

**RCA TUBE  
HANDBOOK  
HB-3**



# **SEMICONDUCTOR DEVICE SECTION**

This Section contains data on semiconductor devices such as transistors and diodes.

*For Further Technical Information, write to  
Commercial Engineering, Semiconductor Division,  
Radio Corporation of America, Somerville, N. J.*



# Table of Contents

Sheets in the RCA Semiconductor Products Handbook are arranged in the Table of Contents in order of appearance in each section. The Index of Types, which follows the Table of Contents, lists type numbers in numerical-alphabetical-numerical sequence.

The Table of Contents and Index of Types may be used to determine:

- (1) location of individual sheets
- (2) completeness of Handbook
- (3) arrangement of Handbook sheets

*Reference is to front of sheet unless otherwise indicated. Date appearing on sheet is identified by month and year (e.g., 8-62).*

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## SEMICONDUCTOR DEVICE SECTION:

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This Index of Types is arranged in numerical-alphabetical-numerical sequence of types.

S = SEMICONDUCTOR DEVICE

\* Type is approaching obsolescence. Not recommended for new-equipment design.

• Discontinued type. Data retained in Handbook for reference purposes only.

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Semiconductor & Materials Division

Somerville, N. J.

World Radio History

INDEX OF  
TYPES 3  
2-61



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## Supplement

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### DISCONTINUED TYPES

The following types have been discontinued. To indicate this fact for your future reference please place a large dot (●) after each of the types in the "Type" column of the Index-of-Types sheets.

2N105	2N457	2N641
2N247	2N544	2N642
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2N456	2N640	





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	S	CURVE 92CM-8581R1		S	TENT. DATA 3, 6-59
	S	CURVE 92CM-8576R1		S	SUGGESTED MOUNTING ARRANGEMENT CE-10053
	S	CURVE 92CM-8573R1		S	RATING CHART III 92CM-9835
2N247....	S	TENT. DATA 1, 12-56		S	CURVE 92CM-9826R1
	S	TENT. DATA 2, 12-56		S	CURVE 92CM-9828
	S	CURVES 92CM-9106R1		S	CURVES 92CS-9834 & 92CS-9830R1
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	S	CURVES 92CS-9622 & 92CS-9621		S	CURVE 92CM-9758
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2N457....	S	TENT. DATA 1, 8-59		S	CURVE 92CM-9107
	S	TENT. DATA 2, 8-59		S	CURVE 92CM-9788
	S	OUTLINE CE-9993	2N641....	S	TENT. DATA 1, 6-59
	S	CURVE 92CM-9826R1		S	TENT. DATA 2, 6-59
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				S	CURVE 92CS-9784
				S	DATA, 6-59

### DISCONTINUED TYPES

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2N105	2N457	2N641
2N247	2N544	2N642
2N331	2N561	2N1014
2N456	2N640	3746





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2N497....	S	DATA 1, 4-61	2N1301...	S	DATA 1, 4-61
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	S	DATA 3, 4-61		S	DATA 5, 4-61
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2N580....	S	DATA, 4-61		S	DATA 2, 4-61
2N581....	S	DATA 1, 6-61		S	DATA 3, 4-61
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	S	DATA 3, 6-61		S	DATA 5, 4-61
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	S	DATA 5, 6-61	2N1906...	S	DATA 1, 6-61
2N1489...	S	DATA 1, 6-61		S	DATA 2, 6-61
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2N1701...	S	DATA 1, 4-61	CR102....	S	DATA, 8-61
	S	DATA 2, 4-61	CR103....	S	DATA, 8-61
	S	DATA 3, 4-61	CR104....	S	DATA, 8-61
2N1702...	S	DATA 1, 4-61	CR105....	S	DATA, 8-61
	S	DATA 2, 4-61	CR106....	S	DATA, 8-61
	S	DATA 3, 4-61	CR107....	S	DATA, 8-61
2N1703...	S	DATA 1, 4-61	CR108....	S	DATA, 8-61
	S	DATA 2, 4-61	CR109....	S	DATA, 8-61
2N1708...	S	DATA 1, 8-61	CR110....	S	DATA, 8-61



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## Supplement

### DELETIONS

For key to symbols, see sheet Index of Types 1

Type	Section	Sheet & Date	Type	Section	Sheet & Date
2N105....	S	TENT. DATA 1, 6-56	2N544....	S	CURVES 92CS-9514 & 92CS-9515
	S	TENT. DATA 2, 6-56	2N561....	S	TENT. DATA 1, 6-59
	S	CURVE 92CM-8572R1		S	TENT. DATA 2, 6-59
	S	CURVE 92CM-8581R1		S	TENT. DATA 3, 6-59
	S	CURVE 92CM-8576R1		S	SUGGESTED MOUNTING AR- RANGEMENT CE-10053
	S	CURVE 92CM-8573R1		S	RATING CHART III 92CM- 9835
2N247....	S	TENT. DATA 1, 12-56		S	CURVE 92CM-9826R1
	S	TENT. DATA 2, 12-56		S	CURVE 92CM-9828
	S	CURVES 92CM-9106R1		S	CURVES 92CS-9834 & 92CS-9830R1
2N331....	S	TENT. DATA 1, 6-59	2N640....	S	TENT. DATA 1, 6-59
	S	TENT. DATA 2, 6-59		S	TENT. DATA 2, 6-59
	S	CURVE 92CS-9596		S	CURVE 92CM-9107
	S	CURVES 92CS-9622 & 92CS-9621		S	CURVE 92CM-9758
2N456....	S	TENT. DATA 1, 8-59	2N641....	S	TENT. DATA 1, 6-59
	S	TENT. DATA 2, 8-59		S	TENT. DATA 2, 6-59
2N457....	S	TENT. DATA 1, 8-59		S	CURVE 92CM-9107
	S	TENT. DATA 2, 8-59	2N641....	S	CURVE 92CM-9788
	S	OUTLINE CE-9993	2N642....	S	TENT. DATA 1, 6-59
	S	CURVE 92CM-9826R1		S	TENT. DATA 2, 6-59
	S	CURVE 92CM-9828		S	CURVE 92CM-9107
	S	CURVES 92CS-9837 & 92CS-9834		S	CURVE 92CS-9784
2N544....	S	TENT. DATA, 4-58	2N1014...	S	DATA, 6-59
	S	OUTLINE & NOTE CE- 9122R3			

### DISCONTINUED TYPES

The following types have been discontinued. To indicate this fact for your future reference please place a large dot (●) after each of the types in the "Type" column of the Index-of-Types sheets.

2N105	2N457	2N641
2N247	2N544	2N642
2N331	2N561	2N1014
2N456	2N640	3746





# Index of Types

## Supplement

### ADDITIONS AND REVISIONS

For key to symbols, see sheet *Index of Types 1*

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IN1183A, IN1183RA	S	DATA 1, 2-62	IN1190, IN1190R	S	DATA, 2-62
	S	DATA 2, 2-62	IN1190...		See IN1190, IN1190R
	S	DATA 3, 2-62			sheet
IN1183RA.		See IN1183A, IN1183RA	2N398A...	S	DATA 1, 2-62
		sheet		S	DATA 2, 2-62
IN1184A, IN1184RA	S	DATA, 2-62	2N955...	S	DATA 1, 2-62
IN1184RA.		See IN1184A, IN1184RA		S	DATA 2, 2-62
		sheet		S	DATA 3, 2-62
IN1186A, IN1186RA	S	DATA, 2-62		S	DATA 4, 2-62
IN1186RA.		See IN1186A, IN1186RA		S	DATA 5, 2-62
		sheet	2N170B...	S	DATA 1, 2-62
IN1187, IN1187R	S	DATA 1, 2-62		S	DATA 2, 2-62
	S	DATA 2, 2-62		S	DATA 3, 2-62
	S	DATA 3, 2-62		S	DATA 4, 2-62
IN1187R..		See IN1187, IN1187R		S	DATA 5, 2-62
		sheet		S	DATA 6, 2-62
IN1188, IN1188R	S	DATA, 2-62	2N2205...	S	DATA, 2-62
IN1188...		See IN1188, IN1188R	2N2206...	S	DATA 1, 2-62
		sheet		S	DATA 2, 2-62
IN1189, IN1189R	S	DATA, 2-62		S	DATA 3, 2-62
IN1189...		See IN1189, IN1189R		S	DATA 4, 2-62
		sheet		S	DATA 5, 2-62
				S	DATA 6, 2-62
				S	DATA 7, 2-62





# Index of Types

## Supplement

### ADDITIONS AND REVISIONS

For key to symbols, see sheet *Index of Types 1*

Type	Section	Sheet & Date	Type	Section	Sheet & Date
IN3754...	S	DATA 1, 8-62	2N2475...	S	DATA 1, 8-62
	S	DATA 2, 8-62		S	DATA 2, 8-62
IN3755...	S	DATA, 8-62		S	DATA 3, 8-62
IN3756...	S	DATA 1, 8-62		S	DATA 4, 8-62
	S	DATA 2, 8-62		S	DATA 5, 8-62
IN3847...	S	DATA 1, 8-62		S	DATA 6, 8-62
	S	DATA 2, 8-62	2N2476...	S	DATA 7, 8-62
IN3848...	S	DATA, 8-62		S	DATA 1, 8-62
IN3849...	S	DATA, 8-62		S	DATA 2, 8-62
IN3850...	S	DATA, 8-62		S	DATA 3, 8-62
IN3851...	S	DATA, 8-62		S	DATA 4, 8-62
IN3852...	S	DATA, 8-62	2N2477...	S	DATA 1, 8-62
IN3853...	S	DATA, 8-62		S	DATA 2, 8-62
IN3854...	S	DATA, 8-62	2N2482...	S	DATA 1, 8-62
IN3855...	S	DATA, 8-62		S	DATA 2, 8-62
IN3856...	S	DATA, 8-62		S	DATA 3, 8-62
IN3857...	S	DATA, 8-62		S	DATA 4, 8-62
IN3858...	S	DATA, 8-62		S	DATA 5, 8-62
IN3859...	S	DATA, 8-62	CR101....	S	DATA 1, 8-62
IN3860...	S	DATA, 8-62		S	DATA 2, 8-62
IN3861...	S	DATA 1, 8-62		S	DATA 3, 8-62
	S	DATA 2, 8-62		S	DATA 4, 8-62
IN3862...	S	DATA, 8-62	CR102....	S	DATA, 8-62
IN3863...	S	DATA, 8-62	CR103....	S	DATA, 8-62
2N398...	S	DATA, 8-62	CR104....	S	DATA 1, 8-62
2N398A...	S	DATA 1, 8-62		S	DATA 2, 8-62
	S	DATA 2, 8-62	CR105....	S	DATA 1, 8-62
2N398B...	S	DATA 1, 8-62		S	DATA 2, 8-62
	S	DATA 2, 8-62	CR106....	S	DATA 1, 8-62
	S	DATA 3, 8-62		S	DATA 2, 8-62
2N709....	S	DATA 1, 8-62	CR107....	S	DATA 1, 8-62
	S	DATA 2, 8-62		S	DATA 2, 8-62
2N955....	S	DATA 1, 8-62	CR108....	S	DATA 1, 8-62
	S	DATA 2, 8-62		S	DATA 2, 8-62
2N955A...	S	DATA 1, 8-62	CR109....	S	DATA 1, 8-62
	S	DATA 2, 8-62		S	DATA 2, 8-62
	S	DATA 3, 8-62	CR110....	S	DATA 1, 8-62
	S	DATA 4, 8-62		S	DATA 2, 8-62
	S	DATA 5, 8-62	CR201....	S	DATA 1, 8-62
	S	DATA 6, 8-62		S	DATA 2, 8-62
2N1853...	S	DATA 1, 8-62		S	DATA 3, 8-62
	S	DATA 2, 8-62	CR203....	S	DATA, 8-62
	S	DATA 3, 8-62	CR204....	S	DATA, 8-62
2N1854...	S	DATA 1, 8-62	CR206....	S	DATA, 8-62
	S	DATA 2, 8-62	CR208....	S	DATA, 8-62
2N2273...	S	DATA 1, 8-62	CR210....	S	DATA, 8-62
	S	DATA 2, 8-62	CR212....	S	DATA, 8-62





# Application Guide for RCA TRANSISTORS

## AUDIO-FREQUENCY APPLICATIONS

<b>SMALL SIGNAL—Class A</b>			
2N104	2N215	2N220	2N1010
2N175			
<b>DRIVER</b>			
2N405	2N406	2N591	
<b>LARGE SIGNAL—Classes A and B</b>			
2N109	2N270	2N408	2N649
2N217	2N407	2N647	
<b>POWER AMPLIFIER</b>			
<i>Dissipations—Up to 4.9 Watts</i>			
●2N497	●2N699	●2N1092	●2N1613
●2N656			
<i>Dissipations—5 to 49.9 Watts</i>			
2N176	2N1183	●2N1480	●2N1700
2N301	2N1183A	●2N1481	●2N1701
2N301A	2N1183B	●2N1482	●2N1768
2N351	2N1184	●2N1483	●2N1769
2N376	2N1184A	●2N1484	●2N2102
●2N1067	2N1184B	●2N1485	●2N2270
●2N1068	●2N1479	●2N1486	
<i>Dissipations—50 Watts and Higher</i>			
2N173	●2N1069	●2N1488	●2N1702
2N174	●2N1070	●2N1489	●2N1703
2N277	2N1099	●2N1490	2N1905
2N278	2N1100	●2N1511	2N1906
2N441	2N1358	●2N1512	●2N2015
2N442	2N1412	●2N1513	●2N2016
2N443	●2N1487	●2N1514	

● Silicon type.

## RADIO-FREQUENCY APPLICATIONS

<b>VHF AMPLIFIER</b>			
2N384	2N1177	2N1396	●2N1491
2N1023	2N1225	2N1397	●2N1492
2N1066			●2N1493
<b>HF AMPLIFIER</b>			
2N274	2N1066	2N1395	●2N1492
2N370	2N1224	2N1396	●2N1493
2N384	2N1225	2N1397	2N1631
●2N708	2N1226	●2N1491	2N1632
2N1023			2N1637
<b>MIXER</b>			
2N274	2N1023	2N1224	2N1395
2N372	2N1066	2N1225	2N1396
2N384	2N1179	2N1226	2N1397
<b>OSCILLATOR</b>			
2N274	2N1023	2N1224	2N1395
2N371	2N1066	2N1225	2N1396
2N384	2N1178	2N1226	2N1397
<b>CONVERTER</b>			
2N140	2N412	2N1226	2N1526
2N219	2N1023	2N1395	2N1527
2N274	2N1066	2N1396	2N1635
2N374	2N1224	2N1397	2N1636
2N384	2N1225	2N1426	2N1639
2N411			
<b>IF AMPLIFIER</b>			
2N139	2N410	2N1225	2N1425
2N218	2N1023	2N1226	2N1524
2N274	2N1066	2N1395	2N1525
2N373	2N1180	2N1396	2N1633
2N384	2N1224	2N1397	2N1634
2N409			2N1638

● Silicon type.

## COMPUTER SWITCHING APPLICATIONS

<i>Stage Delays Greater than 300 Nanoseconds<sup>a</sup></i>			
2N398	2N398A	2N586	
<i>Stage Delays of 100 to 300 Nanoseconds<sup>a</sup></i>			
2N269	2N580	2N1091	2N1306
2N388	2N581	2N1169 <sup>b</sup>	2N1307
2N388A	2N582	2N1170 <sup>b</sup>	2N1308
2N404	2N583	2N1302	2N1309
2N404A	2N584	2N1303	2N1319 <sup>b</sup>
2N414	2N585	2N1304	2N1605
2N578	2N1090	2N1305	2N1605A
2N579			3907/2N404
<i>Stage Delays of 30 to 100 Nanoseconds<sup>a</sup></i>			
●2N696	2N796	2N1215 <sup>c</sup>	2N1301
●2N697	2N1213 <sup>c</sup>	2N1216 <sup>c</sup>	2N1384
2N794	2N1214 <sup>c</sup>	2N1300	2N1683
2N795			
<i>Stage Delays of 10 to 30 Nanoseconds<sup>a</sup></i>			
2N643	●2N706	2N710	2N1450
2N644	●2N706A	2N711	●2N1708
2N645	●2N708	2N828	●2N2205
2N705			●2N2206
<i>Stage Delays of 5 to 10 Nanoseconds<sup>a</sup></i>			
2N955			

<sup>a</sup> Measured in resistor-capacitor-transistor logic circuit except for drift-transistor types 2N643, 2N644, 2N645, and 2N1450 which are measured in transistor-current-steering logic circuit. Nanoseconds = 10<sup>-9</sup> seconds.

<sup>b</sup> Bidirectional type.

<sup>c</sup> Thyristor type.

● Silicon type.



# TRANSISTORS

## POWER SWITCHING APPLICATIONS

*Dissipations—Up to 4.9 Watts*

- 2N497      ●2N699      ●2N1092      ●2N1613
- 2N656

*Dissipations—5 to 49.9 Watts*

- 2N1067      2N1184A      ●2N1482      ●2N1700
- 2N1068      2N1184B      ●2N1483      ●2N1701
- 2N1183      ●2N1479      ●2N1484      ●2N1768
- 2N1183A      ●2N1480      ●2N1485      ●2N1769
- 2N1183B      ●2N1481      ●2N1486      ●2N2102
- 2N1184                           ●2N2270

*Dissipations—50 Watts and Higher*

- 2N173      ●2N1069      ●2N1488      ●2N1702
- 2N174      ●2N1070      ●2N1489      ●2N1703
- 2N277      2N1099      ●2N1490      2N1905
- 2N278      2N1100      ●2N1511      2N1906
- 2N441      2N1358      ●2N1512      ●2N2015
- 2N442      2N1412      ●2N1513      ●2N2016
- 2N443      ●2N1487      ●2N1514

## MILITARY-SPECIFICATION TYPES

- JAN-2N220      Meets MIL-T-19500/1  
dated Jan. 14, 1957
- USA-2N274      Meets MIL-T-19500/26 (Sig C)  
dated Oct. 3, 1957
- USA-2N384      Meets MIL-T-19500/27 (Sig C)  
dated Oct. 14, 1957
- USA-2N706      Meets MIL-S-19500/120 (Sig C)  
dated June 2, 1960
- USA-2N1183      } Meet MIL-S-19500/143 (Sig C)
- USA-2N1183A      } dated Oct. 10, 1960
- USA-2N1183B      }
- USA-2N1184      }
- USA-2N1184A      }
- USA-2N1184B      }
- USA-2N1358      Meets MIL-S-19500 (Sig C)  
dated June 9, 1961
- USAF-2N404      Meets MIL-T-19500/20 USAF  
dated July 23, 1957

TRANSISTORS

● Silicon type.



# Application Guide for RCA TRANSISTORS

## AUDIO-FREQUENCY APPLICATIONS

### SMALL SIGNAL—Class A

2N104	2N215	2N220	2N1010
2N175			

### DRIVER

2N405	2N406	2N591
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### LARGE SIGNAL—Classes A and B

2N109	2N270	2N408	2N649
2N217	2N407	2N647	

### POWER AMPLIFIER

*Dissipations—Up to 4.9 Watts*

●2N497	●2N656	●2N1092
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*Dissipations—5 to 49.9 Watts*

2N176	2N1183	●2N1479	●2N1485
2N301	2N1183A	●2N1480	●2N1486
2N301A	2N1183B	●2N1481	●2N1700
2N351	2N1184	●2N1482	●2N1701
2N376	2N1184A	●2N1483	●2N1768
●2N1067	2N1184B	●2N1484	●2N1769
●2N1068			

*Dissipations—50 Watts and Higher*

2N173	●2N1069	●2N1488	●2N1702
2N174	●2N1070	●2N1489	●2N1703
2N277	2N1099	●2N1490	2N1905
2N278	2N1100	●2N1511	2N1906
2N441	2N1358	●2N1512	●2N2015
2N442	2N1412	●2N1513	●2N2016
2N443	●2N1487	●2N1514	

● Silicon type.

## RADIO-FREQUENCY APPLICATIONS

### VHF AMPLIFIER

2N384	2N1177	2N1396	●2N1491
2N1023	2N1225	2N1397	●2N1492
2N1066			●2N1493

### HF AMPLIFIER

2N274	2N1224	2N1396	●2N1493
2N370	2N1225	2N1397	2N1631
2N384	2N1226	●2N1491	2N1632
2N1023	2N1395	●2N1492	2N1637
2N1066			

### MIXER

2N274	2N1023	2N1224	2N1395
2N372	2N1066	2N1225	2N1396
2N384	2N1179	2N1226	2N1397

### OSCILLATOR

2N274	2N1023	2N1224	2N1395
2N371	2N1066	2N1225	2N1396
2N384	2N1178	2N1226	2N1397

### CONVERTER

2N140	2N412	2N1226	2N1526
2N219	2N1023	2N1395	2N1527
2N274	2N1066	2N1396	2N1635
2N374	2N1224	2N1397	2N1636
2N384	2N1225	2N1426	2N1639
2N411			

### IF AMPLIFIER

2N139	2N410	2N1225	2N1425
2N218	2N1023	2N1226	2N1524
2N274	2N1066	2N1395	2N1525
2N373	2N1180	2N1396	2N1633
2N384	2N1224	2N1397	2N1634
2N409			2N1638



# TRANSISTORS

## COMPUTER SWITCHING APPLICATIONS

*Stage Delays Greater than 300 Nanoseconds<sup>a</sup>*

2N398            2N586

*Stage Delays of 100 to 300 Nanoseconds<sup>a</sup>*

2N269	2N579	2N583	2N1091
2N404	2N580	2N584	2N1169 <sup>b</sup>
2N404A	2N581	2N585	2N1170 <sup>b</sup>
2N414	2N582	2N1090	2N1319 <sup>b</sup>
2N578			3907/2N404

*Stage Delays of 30 to 100 Nanoseconds<sup>a</sup>*

2N794	2N934	2N1215 <sup>C</sup>	2N1301
2N795	2N1213 <sup>C</sup>	2N1216 <sup>C</sup>	2N1384
2N796	2N1214 <sup>C</sup>	2N1300	2N1683

*Stage Delays of 10 to 30 Nanoseconds<sup>a</sup>*

2N643	2N705	●2N706A	2N711
2N644	●2N706	2N710	2N1450
2N645			

<sup>a</sup> Measured in resistor-capacitor-transistor logic circuit except for very high speed drift-transistor types 2N643, 2N644, 2N645, and 2N1450 which are measured in transistor current steering logic circuit. Nanoseconds = 10<sup>-9</sup> seconds.

<sup>b</sup> Bidirectional type.

<sup>c</sup> Thyristor type.

● Silicon type.

## POWER SWITCHING APPLICATIONS

*Dissipations—Up to 4.9 Watts*

●2N497            ●2N656            ●2N1092

*Dissipations—5 to 49.9 Watts*

●2N1067	2N1184	●2N1481	●2N1486
●2N1068	2N1184A	●2N1482	●2N1700
2N1183	2N1184B	●2N1483	●2N1701
2N1183A	●2N1479	●2N1484	●2N1768
2N1183B	●2N1480	●2N1485	●2N1769

*Dissipations—50 Watts and Higher*

2N173	●2N1069	●2N1488	●2N1702
2N174	●2N1070	●2N1489	●2N1703
2N277	2N1099	●2N1490	2N1905
2N278	2N1100	●2N1511	2N1906
2N441	2N1358	●2N1512	●2N2015
2N442	2N1412	●2N1513	●2N2016
2N443	●2N1487	●2N1514	

## MILITARY-SPECIFICATION TYPES


JAN-2N220	Meets MIL-T-19500/1 dated Jan. 14, 1957
USA-2N274	Meets MIL-T-19500/26 (Sig C) dated Oct. 3, 1957
USA-2N384	Meets MIL-T-19500/27 (Sig C) dated Oct. 14, 1957
USAF-2N404	Meets MIL-T-19500/20 USAF dated July 23, 1957
USA-2N706	Meets MIL-S-19500/120 (Sig C) dated June 2, 1960






# Application Guide for RCA SILICON RECTIFIERS


## RECTIFIER APPLICATIONS

MAXIMUM DC FORWARD AMPERES <sup>a</sup> at indicated temperature <sup>b</sup> (°C)		MAXIMUM PEAK INVERSE VOLTS	MAXIMUM OPERATING TEMPERATURE <sup>b</sup> (°C)		TYPE
<i>Forward Currents—Up to 0.750 Ampere</i>					
0.500 <sup>c</sup>	≤75	T <sub>A</sub>	400	100 T <sub>A</sub>	1N1763
0.500 <sup>c</sup>	≤75	T <sub>A</sub>	500	100 T <sub>A</sub>	1N1764
0.500		T <sub>A</sub>	800	100 T <sub>A</sub>	1N3196
0.400 <sup>c</sup>	≤75	T <sub>A</sub>		100 T <sub>A</sub>	1N3256
0.750		T <sub>A</sub>	50	125 T <sub>A</sub>	1N2858
0.500 <sup>c</sup>	≤75	T <sub>A</sub>	100	125 T <sub>A</sub>	1N2859
0.750		T <sub>A</sub>	200	125 T <sub>A</sub>	1N2860
0.500 <sup>c</sup>	≤75	T <sub>A</sub>	300	125 T <sub>A</sub>	1N2861
0.750		T <sub>A</sub>	400	125 T <sub>A</sub>	1N2862
0.500 <sup>c</sup>	≤75	T <sub>A</sub>	400	125 T <sub>A</sub>	1N2862
0.750		T <sub>A</sub>	500	125 T <sub>A</sub>	1N2863
0.500 <sup>c</sup>	≤75	T <sub>A</sub>	600	125 T <sub>A</sub>	1N2864
0.750		T <sub>A</sub>	200	100 T <sub>A</sub>	1N3193
0.500 <sup>c</sup>	≤75	T <sub>A</sub>	200	100 T <sub>A</sub>	1N3253
0.750		T <sub>A</sub>	400	100 T <sub>A</sub>	1N3194
0.500 <sup>c</sup>	≤75	T <sub>A</sub>	400	100 T <sub>A</sub>	1N3254
0.750		T <sub>A</sub>	600	100 T <sub>A</sub>	1N3195
0.500 <sup>c</sup>	≤75	T <sub>A</sub>	600	100 T <sub>A</sub>	1N3255
0.750	≤50	T <sub>A</sub>	100	165 T <sub>A</sub>	1N440B
0.750	≤50	T <sub>A</sub>	200	165 T <sub>A</sub>	1N441B
0.750	≤50	T <sub>A</sub>	300	165 T <sub>A</sub>	1N442B
0.750	≤50	T <sub>A</sub>	400	165 T <sub>A</sub>	1N443B
0.750	≤35	T <sub>A</sub>	500	150 T <sub>A</sub>	1N444B

## RECTIFIER APPLICATIONS


MAXIMUM DC FORWARD AMPERES <sup>a</sup> at indicated temperature <sup>b</sup> (°C)		MAXIMUM PEAK INVERSE VOLTS	MAXIMUM OPERATING TEMPERATURE <sup>b</sup> (°C)		TYPE
0.750	≤35	T <sub>A</sub>	600	150 T <sub>A</sub>	1N445B
0.750	≤50	T <sub>A</sub>	50	165 T <sub>A</sub>	1N536
0.750	≤50	T <sub>A</sub>	100	165 T <sub>A</sub>	1N537
0.750	≤50	T <sub>A</sub>	200	165 T <sub>A</sub>	1N538
0.750	≤50	T <sub>A</sub>	300	165 T <sub>A</sub>	1N539
0.750	≤50	T <sub>A</sub>	400	165 T <sub>A</sub>	1N540
0.750	≤50	T <sub>A</sub>	600	165 T <sub>A</sub>	1N547
0.750	≤50	T <sub>A</sub>	500	165 T <sub>A</sub>	1N1095
<i>Forward Currents—1 to 40 Amperes</i>					
5	135	T <sub>C</sub>	50	175 T <sub>C</sub>	1N1612, 1N1612R
5	135	T <sub>C</sub>	100	175 T <sub>C</sub>	1N1613, 1N1613R
5	135	T <sub>C</sub>	200	175 T <sub>C</sub>	1N1614, 1N1614R
5	135	T <sub>C</sub>	400	175 T <sub>C</sub>	1N1615, 1N1615R
5	135	T <sub>C</sub>	600	175 T <sub>C</sub>	1N1616, 1N1616R
12	150	T <sub>C</sub>	50 100 <sup>d</sup>	200 T <sub>C</sub>	1N1199A, 1N1199RA
12	150	T <sub>C</sub>	100 200 <sup>d</sup>	200 T <sub>C</sub>	1N1200A, 1N1200RA
12	150	T <sub>C</sub>	200 350 <sup>d</sup>	200 T <sub>C</sub>	1N1202A, 1N1202RA
12	150	T <sub>C</sub>	300 450 <sup>d</sup>	200 T <sub>C</sub>	1N1203A, 1N1203RA
12	150	T <sub>C</sub>	400 600 <sup>d</sup>	200 T <sub>C</sub>	1N1204A, 1N1204RA

## RECTIFIER APPLICATIONS

MAXIMUM DC FORWARD AMPERES <sup>a</sup> at indicated temperature <sup>b</sup> (°C)		MAXIMUM PEAK INVERSE VOLTS	MAXIMUM OPERATING TEMPERATURE <sup>b</sup> (°C)		TYPE
12	150	T <sub>C</sub>	500 700 <sup>d</sup>	200 T <sub>C</sub>	1N1205A, 1N1205RA
12	150	T <sub>C</sub>	600 800 <sup>d</sup>	200 T <sub>C</sub>	1N1206A, 1N1206RA
20	150	T <sub>C</sub>	55	175 T <sub>C</sub>	1N248C, 1N248RC
20	150	T <sub>C</sub>	110	175 T <sub>C</sub>	1N249C, 1N249RC
20	150	T <sub>C</sub>	220	175 T <sub>C</sub>	1N250C, 1N250RC
20	150	T <sub>C</sub>	300	175 T <sub>C</sub>	1N1195A, 1N1195RA
20	150	T <sub>C</sub>	400	175 T <sub>C</sub>	1N1196A, 1N1196RA
20	150	T <sub>C</sub>	500	175 T <sub>C</sub>	1N1197A, 1N1197RA
20	150	T <sub>C</sub>	600	175 T <sub>C</sub>	1N1198A, 1N1198RA
35	140	T <sub>C</sub>	300	175 T <sub>C</sub>	1N1187, 1N1187R
35	140	T <sub>C</sub>	400	175 T <sub>C</sub>	1N1188, 1N1188R
35	140	T <sub>C</sub>	500	175 T <sub>C</sub>	1N1189, 1N1189R
35	140	T <sub>C</sub>	600	175 T <sub>C</sub>	1N1190, 1N1190R

- <sup>a</sup> With resistive or inductive load except as noted.  
<sup>b</sup> T<sub>A</sub> = ambient temperature, T<sub>C</sub> = case temperature.  
<sup>c</sup> With capacitive load.  
<sup>d</sup> Transient voltage rating.

RECTIFIER APPLICATIONS

MAXIMUM DC FORWARD AMPERES <sup>a</sup> at indicated temperature <sup>b</sup> (°C)	MAXIMUM PEAK INVERSE VOLTS	MAXIMUM OPERATING TEMPERATURE <sup>b</sup> (°C)		TYPE
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Forward Currents—1 to 40 Amperes

40	150 T <sub>C</sub>	50	200 T <sub>C</sub>	1N1183A, 1N1183RA
40	150 T <sub>C</sub>	100	200 T <sub>C</sub>	1N1184A, 1N1184RA
40	150 T <sub>C</sub>	200	200 T <sub>C</sub>	1N1186A, 1N1186RA

Peak Inverse Voltages—Up to 10000 Volts

0.825	60 T <sub>A</sub>	1200	125 T <sub>A</sub>	CR101
0.825	60 T <sub>A</sub>	2000	125 T <sub>A</sub>	CR102
0.715	60 T <sub>A</sub>	3000	125 T <sub>A</sub>	CR103
0.605	60 T <sub>A</sub>	4000	125 T <sub>A</sub>	CR104
0.605	60 T <sub>A</sub>	5000	125 T <sub>A</sub>	CR105
0.550	60 T <sub>A</sub>	6000	125 T <sub>A</sub>	CR106
0.550	60 T <sub>A</sub>	7000	125 T <sub>A</sub>	CR107
0.550	60 T <sub>A</sub>	8000	125 T <sub>A</sub>	CR108
0.550	60 T <sub>A</sub>	9000	125 T <sub>A</sub>	CR109
0.550	60 T <sub>A</sub>	10000	125 T <sub>A</sub>	CR110

MILITARY-SPECIFICATION TYPES

JAN-1N538	Meets MIL-E-1/1084A dated Jan.28, 1958
JAN-1N540	Meets MIL-E-1/1085A dated Jan.28, 1958
JAN-1N547	Meets MIL-E-1/1083A dated Jan.28, 1958
USA-1N249B	} Meet MIL-S-19500/134 (Sig C) dated Aug.9, 1960
USA-1N250B	
USA-1N2135A	

TEMPERATURE- AND VOLTAGE-COMPENSATION APPLICATIONS

1N2326

COMPUTER APPLICATIONS

GERMANIUM TUNNEL DIODES

1N3128  
1N3129  
1N3130

GALLIUM-ARSENIDE TUNNEL DIODE

1N3138

GERMANIUM MULTIPLE DIODES

2DG001 (Twin)  
3DG001 (Triple)

<sup>a</sup> With resistive or inductive load except as noted.  
<sup>b</sup> T<sub>A</sub> = ambient temperature, T<sub>C</sub> = case temperature.



## AUDIO-FREQUENCY APPLICATIONS

### SMALL SIGNAL—Class A

2N104	2N215	2N220	2N1010
2N175			

### DRIVER

2N405	2N406	2N591
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### LARGE SIGNAL—Classes A and B

2N109	2N270	2N408	2N649
2N217	2N407	2N647	

### POWER AMPLIFIER

*Dissipations—Up to 4.9 Watts*

•2N497	•2N1092	•2N1480	•2N1482
•2N656	•2N1479	•2N1481	

*Dissipations—5 to 49.9 Watts*

2N176	•2N1068	2N1184-A	•2N1486
2N301	2N1183	2N1184-B	•2N1700
2N301-A	2N1183-A	•2N1483	•2N1701
2N351	2N1183-B	•2N1484	•2N1768
2N376	2N1184	•2N1485	•2N1769
•2N1067			

*Dissipations—50 Watts and Higher*

2N173	•2N1069	•2N1487	•2N1513
2N174	•2N1070	•2N1488	•2N1514
2N277	2N1099	•2N1489	•2N1702
2N278	2N1100	•2N1490	•2N1703
2N441	2N1358	•2N1511	2N1905
2N442	2N1412	•2N1512	2N1906
2N443			

## RADIO-FREQUENCY APPLICATIONS

### VHF AMPLIFIER

2N384	2N1177	2N1396	•2N1491
2N1023	2N1225	2N1397	•2N1492
2N1066			•2N1493

### HF AMPLIFIER

2N274	2N1224	2N1396	•2N1493
2N370	2N1225	2N1397	2N1631
2N384	2N1226	•2N1491	2N1632
2N1023	2N1395	•2N1492	2N1637
2N1066			

### MIXER

2N274	2N1023	2N1224	2N1395
2N372	2N1066	2N1225	2N1396
2N384	2N1179	2N1226	2N1397

### OSCILLATOR

2N274	2N1023	2N1224	2N1395
2N371	2N1066	2N1225	2N1396
2N384	2N1178	2N1226	2N1397

### CONVERTER

2N140	2N412	2N1226	2N1526
2N219	2N1023	2N1395	2N1527
2N274	2N1066	2N1396	2N1635
2N374	2N1224	2N1397	2N1636
2N384	2N1225	2N1426	2N1639
2N411			

### IF AMPLIFIER

2N139	2N410	2N1225	2N1425
2N218	2N1023	2N1226	2N1524
2N274	2N1066	2N1395	2N1525
2N373	2N1180	2N1396	2N1633
2N384	2N1224	2N1397	2N1634
2N409			2N1638

## COMPUTER SWITCHING APPLICATIONS

*Stage Delays Greater than 300 Nanoseconds<sup>a</sup>*

2N398	2N586
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*Stage Delays of 100 to 300 Nanoseconds<sup>a</sup>*

2N269	2N580	2N584	2N1169 <sup>b</sup>
2N404	2N581	2N585	2N1170 <sup>b</sup>
2N414	2N582	2N1090	2N1319 <sup>b</sup>
2N578	2N583	2N1091	3907/2N404
2N579			

*Stage Delays of 30 to 100 Nanoseconds<sup>a</sup>*

2N794	2N934	2N1215 <sup>c</sup>	2N1301
2N795	2N1213 <sup>c</sup>	2N1216 <sup>c</sup>	2N1384
2N796	2N1214 <sup>c</sup>	2N1300	2N1683

*Stage Delays of 10 to 30 Nanoseconds<sup>a</sup>*

2N643	2N705	•2N706-A	2N711
2N644	•2N706	2N710	2N1450
2N645			

*Stage Delays Less than 10 Nanoseconds<sup>a</sup>*

2N931	2N932
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## POWER SWITCHING APPLICATIONS

*Dissipations—Up to 4.9 Watts*

•2N497	•2N1092	•2N1480	•2N1482
•2N656	•2N1479	•2N1481	

*Dissipations—5 to 49.9 Watts*

•2N1067	2N1183-B	•2N1483	•2N1700
•2N1068	2N1184	•2N1484	•2N1701
2N1183	2N1184-A	•2N1485	•2N1768
2N1183-A	2N1184-B	•2N1486	•2N1769

*Dissipations—50 Watts and Higher*

2N173	•2N1069	•2N1487	•2N1513
2N174	•2N1070	•2N1488	•2N1514
2N277	2N1099	•2N1489	•2N1702
2N278	2N1100	•2N1490	•2N1703
2N441	2N1358	•2N1511	2N1905
2N442	2N1412	•2N1512	2N1906
2N443			

<sup>a</sup> Measured in resistor-capacitor-transistor logic circuit except for very high speed drift-transistor types 2N643, 2N644, 2N645, and 2N1450 which are measured in transistor current steering logic circuit. Nanoseconds = 10<sup>-9</sup> seconds.

<sup>b</sup> Bidirectional type.

<sup>c</sup> Thyristor type.

• Silicon type.

# SILICON RECTIFIERS

## RECTIFIER APPLICATIONS

MAXIMUM DC FORWARD AMPERES <sup>a</sup> at indicated temperature <sup>b</sup> (°C)	MAXIMUM PEAK INVERSE VOLTS	MAXIMUM OPERATING TEMPERATURE <sup>c</sup> (°C)	TYPE
20	150 T <sub>C</sub>	55	175 T <sub>C</sub>
20	150 T <sub>C</sub>	110	175 T <sub>C</sub>
20	150 T <sub>C</sub>	220	175 T <sub>C</sub>
0.750	150 T <sub>A</sub>	100	165 T <sub>A</sub>
0.750	150 T <sub>A</sub>	200	165 T <sub>A</sub>
0.750	150 T <sub>A</sub>	300	165 T <sub>A</sub>
0.750	150 T <sub>A</sub>	400	165 T <sub>A</sub>
0.750	150 T <sub>A</sub>	500	150 T <sub>A</sub>
0.750	150 T <sub>A</sub>	600	150 T <sub>A</sub>
0.750	150 T <sub>A</sub>	50	165 T <sub>A</sub>
0.750	150 T <sub>A</sub>	100	165 T <sub>A</sub>
0.750	150 T <sub>A</sub>	200	165 T <sub>A</sub>
0.750	150 T <sub>A</sub>	300	165 T <sub>A</sub>
0.750	150 T <sub>A</sub>	400	165 T <sub>A</sub>
0.750	150 T <sub>A</sub>	600	165 T <sub>A</sub>
0.750	150 T <sub>A</sub>	500	165 T <sub>A</sub>
20	150 T <sub>C</sub>	300	175 T <sub>C</sub>
20	150 T <sub>C</sub>	400	175 T <sub>C</sub>
20	150 T <sub>C</sub>	500	175 T <sub>C</sub>
20	150 T <sub>C</sub>	600	175 T <sub>C</sub>
0.500 <sup>c</sup>	175 T <sub>A</sub>	400	100 T <sub>A</sub>
0.500 <sup>c</sup>	175 T <sub>A</sub>	500	100 T <sub>A</sub>
0.750	≤75 T <sub>A</sub>	50	125 T <sub>A</sub>
0.500 <sup>c</sup>	≤75 T <sub>A</sub>	100	125 T <sub>A</sub>
0.750	≤75 T <sub>A</sub>	200	125 T <sub>A</sub>
0.500 <sup>c</sup>	≤75 T <sub>A</sub>	300	125 T <sub>A</sub>
0.750	≤75 T <sub>A</sub>	400	125 T <sub>A</sub>
0.500 <sup>c</sup>	≤75 T <sub>A</sub>	500	125 T <sub>A</sub>
0.750	≤75 T <sub>A</sub>	600	125 T <sub>A</sub>
0.500 <sup>c</sup>	≤75 T <sub>A</sub>	200	100 T <sub>A</sub>
0.750	≤75 T <sub>A</sub>	400	100 T <sub>A</sub>
0.500 <sup>c</sup>	≤75 T <sub>A</sub>	600	100 T <sub>A</sub>
0.500	≤75 T <sub>A</sub>	800	100 T <sub>A</sub>

<sup>a</sup> With resistive or inductive load except as noted.  
<sup>b</sup> T<sub>A</sub> = ambient temperature, T<sub>C</sub> = case temperature.  
<sup>c</sup> With capacitive load.

# DIODES

## TEMPERATURE- AND VOLTAGE-COMPENSATION APPLICATIONS

1N2326

## COMPUTER APPLICATIONS

### GERMANIUM TUNNEL DIODES

1N3128  
 1N3129  
 1N3130

### GALLIUM-ARSENIDE TUNNEL DIODE

1N3138

1N248-C, 1N248-PC  
 1N249-C, 1N249-PC  
 1N250-C, 1N250-PC  
 1N440-B  
 1N441-B  
 1N442-B  
 1N443-B  
 1N444-B  
 1N445-B  
 1N536  
 1N537  
 1N538  
 1N539  
 1N540  
 1N547  
 1N1095  
 1N1195-A, 1N1195-RA  
 1N1196-A, 1N1196-RA  
 1N1197-A, 1N1197-RA  
 1N1198-A, 1N1198-RA

1N1763  
 1N1764

1N2858

1N2859

1N2860

1N2861

1N2862

1N2863

1N2864

1N3193

1N3194

1N3195

1N3196

# MILITARY-SPECIFICATION TYPES

## TRANSISTORS

JAN-2N220 Meets MIL-T-19500/1 dated Jan.14, 1957  
 USA-2N274 Meets MIL-T-19500/26 (Sig C) dated Oct.3, 1957  
 USA-2N384 Meets MIL-T-19500/27 (Sig C) dated Oct.14, 1957  
 USAF-2N404 Meets MIL-T-19500/20 USAF dated July 23, 1957  
 USA-2N706 Meets MIL-T-19500/120 (Sig C) dated Jan.4, 1961

## SILICON RECTIFIERS

JAN-1N538 Meets MIL-E-1/1084A dated Jan.28, 1958  
 JAN-1N540 Meets MIL-E-1/1085A dated Jan.28, 1958



# Information on Prices

Information on prices of RCA semiconductor devices described in this Handbook may be obtained from your local RCA Semiconductor Distributor or from your RCA Equipment Sales Representative, who may be reached at the following RCA Equipment Sales Offices:

(East) 744 Broad Street  
Newark 2, New Jersey  
Humboldt 5-3900

605 Marlton Pike  
Erlton, New Jersey  
HAzel 8-4802

731 James Street  
Room 402  
Syracuse 3, New York  
GRanite 4-5591

Greater Baltimore Area  
ENterprise 9-1850

(Northeast) 64 "A" Street  
Needham Heights 94, Massachusetts  
Hillcrest 4-7200

(Southeast) Suite 1  
1520 Edgewater Drive  
Orlando, Florida  
GArden 4-4768

(East Central) 714 New Center Building  
Detroit 2, Michigan  
TRinity 5-5600

(Central) Suite 1154  
Merchandise Mart Plaza  
Chicago 54, Illinois  
WHitehall 4-2900

2132 East 52nd Street  
Indianapolis 5, Indiana  
CLifford 1-1405

5805 Excelsior Boulevard  
Minneapolis 16, Minnesota  
WEst 9-0676

(West) 6801 East Washington Boulevard  
Los Angeles 22, California  
RAYmond 3-8361

1838 El Camino Real  
Burlingame, California  
OXford 7-1620

(Southwest) 7905 Carpenter Freeway  
Dallas 7, Texas  
MElrose 1-9720



# Information on Prices

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(Government) Route 202  
Somerville, New Jersey  
RAndolph 2-3200

1725 "K" Street, Northwest  
Washington 6, D.C.  
FEderal 7-8500

224 North Wilkinson Street  
Dayton 2, Ohio  
BAldwin 6-2366

## EXPORT

(International) Radio Corporation of America  
RCA International Division  
Electronic-Components Marketing Operations  
30 Rockefeller Plaza  
New York 20, New York (U.S.A.)



# Transistor-Dissipation Rating Chart

## Pulse or Switching Service

From Table I:

$$T_{J\text{MAX}} = 175^{\circ}\text{C}$$

$$\tau_1 = 8 \text{ milliseconds} = 8 \times 10^{-3} \text{ second}$$

$$R_{T\text{MAX}} = 75^{\circ}\text{C/watt}$$

Then:

$$t_o/\tau_1 = 10^{-3}/8 \times 10^{-3} = 1.25 \times 10^{-1}$$

$$d = t_o \times \text{PRR} = (10^{-3})(10^1) = 10^{-2} = 0.01$$

Entering the Chart with  $t_o/\tau_1 = 1.25 \times 10^{-1}$  and  $d = 0.01$ , read  $Y = 2.5 \times 10^{-1}$ . Solving for  $T_o$  in the equation:

$$T_o = T_{J\text{MAX}} - P_{\text{MAX}} Y R_{T\text{MAX}}$$

$$T_o = 175 - (3)(2.5 \times 10^{-1})(75) = 119^{\circ}\text{C}$$

Solving for  $\Delta T_{J\text{MAX}}$  in the equation:

$$\Delta T_{J\text{MAX}} = T_{J\text{MAX}} - T_o$$

$$\Delta T_{J\text{MAX}} = 175 - 119 = 56^{\circ}\text{C}$$

**TABLE I**

RCA TRANSISTOR TYPE	MAXIMUM JUNCTION OR STORAGE TEMPERATURE $T_{J\text{MAX}}$ ( $^{\circ}\text{C}$ )	THERMAL TIME CONSTANT $\tau_1$ (msec)	MAXIMUM THERMAL RESISTANCE $R_{T\text{MAX}}$ ( $^{\circ}\text{C/WATT}$ ) COLLECTOR JUNCTION TO:		
			FREE AMBIENT AIR	CASE	MOUNTING FLANGE
2N169	85	12	400	-	-
2N139	85	10	750	-	-
2N140	85	10	750	-	-
2N217	85	12	400	-	-
2N218	85	10	750	-	-
2N219	85	10	750	-	-
2N269	85	10	500	-	-
2N270	85	12	320	-	-
2N274	100	12	620	310	-
2N384	100	10	620	310	-
2N398	85	12	750	-	-
2N404	85	10	500	-	-
2N578	85	15	500	-	-
2N579	85	15	500	-	-



# Transistor-Dissipation Rating Chart

## Pulse or Switching Service

RCA TRANSISTOR TYPE	MAXIMUM JUNCTION OR STORAGE TEMPERATURE $T_{JMAX}$ (°C)	THERMAL TIME CONSTANT $\tau_1$ (msec)	MAXIMUM THERMAL RESISTANCE $R_{TMAX}$ (°C/WATT) COLLECTOR JUNCTION TO:		
			FREE AMBIENT AIR	CASE	MOUNTING FLANGE
2N580	85	15	500	-	-
2N581	85	10	500	-	-
2N582	85	10	500	-	-
2N583	85	10	500	-	-
2N584	85	10	500	-	-
2N585	85	12	500	-	-
2N586	85	12	240	-	-
2N643	85	10	500	-	-
2N644	85	10	500	-	-
2N645	85	10	500	-	-
2N1023	100	10	620	310	-
2N1066	100	10	620	310	-
2N1067	175	8	100	30	-
2N1068	175	8	100	15	-
2N1069	175	10	-	-	3
2N1070	175	10	-	-	3
2N1090	85	12	500	-	-
2N1091	85	12	500	-	-
2N1092	175	8	225	75	-
2N1183	100	8	75	10	-
2N1183-A	100	8	75	10	-
2N1183-B	100	8	75	10	-
2N1184	100	8	75	10	-
2N1184-A	100	8	75	10	-
2N1184-B	100	8	75	10	-
2N1224	100	10	620	310	-
2N1225	100	10	620	310	-
2N1226	100	10	620	310	-
2N1300	85	10	400	-	-
2N1301	85	10	400	-	-
2N1395	100	10	620	310	-
2N1396	100	10	620	310	-
2N1397	100	10	620	310	-

For transistor types not listed in Table I above, refer to the data sheets for the specific type for the required values.







# CLASSIFICATION CHART FOR TYPES IN SEMICONDUCTOR DEVICE SECTION

## JUNCTION TRANSISTORS

### Germanium P-N-P Alloy Types

*For small-signal af applications*

2N77<sup>■</sup>  
2N104  
2N105<sup>■</sup>  
2N175<sup>▲</sup>  
2N206<sup>■</sup>  
2N215<sup>■</sup>  
2N220<sup>■▲</sup>

*For af driver-amplifier applications*

2N405  
2N406<sup>■</sup>

*For large-signal af applications*

2N109  
2N217<sup>■</sup>  
2N270<sup>■</sup>  
2N407  
2N408<sup>■</sup>

*For af power applications*

2N301  
2N301-A

*For 455-kc af applications*

2N139  
2N218<sup>■</sup>  
2N409  
2N410<sup>■</sup>

*For 540- to 1600-kc converter applications*

2N140  
2N219<sup>■</sup>  
2N411  
2N412<sup>■</sup>

*For rf amplifier applications*

2N247<sup>■</sup>  
2N274<sup>■</sup>  
2N370<sup>■</sup>  
2N384<sup>■</sup>  
2N544<sup>■</sup>

*For rf oscillator applications*

2N371<sup>■</sup>

*For rf mixer applications*

2N372<sup>■</sup>

■, ▲: See next page.



# CLASSIFICATION CHART FOR TYPES IN SEMICONDUCTOR DEVICE SECTION

## JUNCTION TRANSISTORS (Cont'd)

*For "on-off" control applications*

2N269<sup>■</sup>  
2N398<sup>■</sup>  
2N404<sup>■</sup>

## SEMICONDUCTOR DIODES

**Germanium Point-Contact Types**

*For low-power-rectification applications*

1N34-A

*For large-signal applications*

1N38-A  
1N58-A

*For applications requiring high back resistance*

1N54-A

■ Flexible-lead type.

▲ Low-noise type.



## RCA TRANSISTORS NOT RECOMMENDED For New Equipment Design

*Certain transistors should be avoided in the design of new equipment because they are approaching obsolescence or have limited or dwindling demand. Such RCA types are listed below for the benefit of equipment designers.*

### JUNCTION TRANSISTORS

2N77





## TENTATIVE DEFINITIONS OF SEMICONDUCTOR DEVICE TERMS

**Current Transfer Ratio.** The quotient of the change of output current with ac output circuit shorted divided by the change in input current producing the change in output current. The current components are understood to be small enough so that linear relations hold between them.

**Large-Signal DC Current Transfer Ratio.** The quotient of the dc output current with the dc output circuit shorted divided by the dc input current producing the dc output current.

**Circuit Stability Factor.** The quotient of the change of dc collector current divided by the change in collector saturation current producing the change in dc collector current.

**Collector Saturation Current.** The temperature-sensitive dc collector current that flows when a dc collector-to-base voltage greater than -0.2 volt is applied with emitter circuit open.

**Class A Amplifier.** An amplifier in which the bias of the input electrode and the alternating input signal are such that output current flows at all times.

**Class B Amplifier.** An amplifier in which the bias of the input electrode is such that the output current is approximately zero when no alternating input signal is applied, and such that when an alternating input signal is applied, the output current flows approximately one-half cycle.

**Collector Transition Capacitance.** The capacitance across the collector-to-base transition region. (A transition region is a region between two homogeneous semiconductor regions, in which the impurity concentration changes).

**Unilateralization.** Unilateralization is a special case of neutralization in that the feedback parameters are completely balanced out. In the case of transistors, these feedback parameters include a resistive component in addition to a capacitive component. Unilateralization changes a bilateral network into a unilateral network.





## TRANSISTORS

Transistors are a new form of electron device. They can perform many of the functions of an electron tube and, in addition, can do some things better and more efficiently than electron tubes. Unlike electron tubes which depend for their functioning on the flow of electrons through a vacuum, a gas, or a vapor, transistors make use of the flow of electrons in a solid — a semiconductor.

A semiconductor is a material having a conductivity lower than that of metals but higher than that of insulators. There are many varieties of semiconductors, but the one employed for the transistors described in this section is germanium. Germanium in its very purest state behaves like an insulator, but its conductivity can be increased by the addition of exact but almost infinitesimal amounts of certain impurities. Peculiarly, the manner in which a germanium crystal conducts can be changed by the choice of the impurity. Thus, by the addition of the proper amount of certain impurities to pure germanium, its conductivity is increased because a surplus of electrons which can migrate freely through the crystal is provided. A conducting germanium crystal so made is identified as *n*-type because it depends on negative particles of electricity, electrons, for conduction.

On the other hand, the addition of other impurities provides a deficiency of electrons which effectively behave like positive particles of electricity. This deficiency of electrons leaves vacancies or holes in the crystal structure. These holes which are free to migrate can carry current but in a direction opposite to that of the *n*-type crystal. Because these carriers of the conduction current are positive in nature, a germanium crystal of this type is identified as *p*-type.

It should be noted that whereas electron tubes depend ordinarily on electrons for conduction, transistors not only make use of electrons but also of holes for obtaining conduction.

The transistors described in this section make use of both kinds of conduction and employ two different types of structures. These two types of structures are identified as "point-contact" and "junction".

Fig. 1 shows the structure of a point-contact transistor. It consists of a crystal of *n*-type germanium having three electrical contacts. Two of these are point contacts and are known as the emitter and collector. A third, the



# TRANSISTORS

base, makes area contact with the germanium crystal. The complete assembly is encased in plastic to provide ruggedness and freedom from atmospheric contaminants.

Fig.1 also shows the point-contact transistor connected in a simple circuit in which the base connection serves as the common return for the input circuit and the output circuit. The input circuit on the left is completed through the battery, the emitter, and the germanium crystal to the base connection. When a positive voltage is applied to the emitter, electrons will be drawn from the crystal into the emitter and thus leave holes in the crystal structure. Under the influence of the negative field of the collector, these holes flow to the collector and thereby increase the collector current appreciably. Or as is sometimes stated, the emitter electrode injects holes into the germanium crystal. Holes near the collector allow electrons to pass into the crystal. Some of these electrons neutralize the holes; others flow to the base connection and thus complete the circuit.

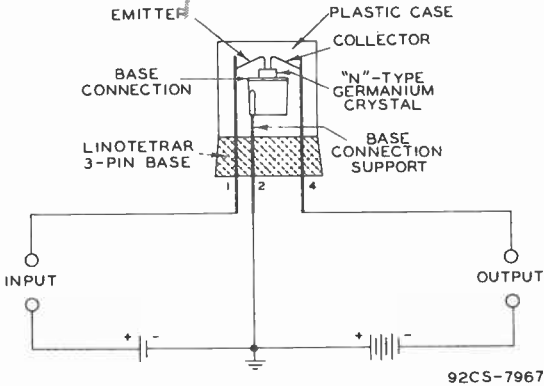


Fig.2 - Diagrammatic Sketch Showing Structural Arrangement of Type 2N32 or Type 2N33 with Associated Simple Circuit.

If the assumption is made that every unit of hole current which leaves the emitter reaches the collector, it follows that a small change in emitter current will result in an equivalent change in collector current, and consequently produce a current amplification factor of one. The current



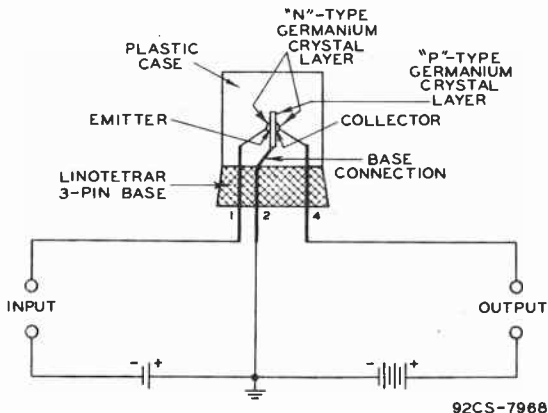


## TRANSISTORS

amplification factor or "alpha" of a transistor is defined as the ratio of change in collector current to a change in emitter current when collector voltage is maintained constant. In point-contact transistors "alpha" is greater than unity; in junction-type transistors, it is less than but approaches unity.

If the germanium crystal employed in Fig.1 is of the *p*-type, a negative voltage is applied to the emitter and holes will be drawn from the crystal into the emitter and thus leave an excess of electrons in the crystal structure. Under the influence of the positive field of the collector, these electrons flow through the crystal to the collector. In general, the *p*-type germanium crystal has characteristics similar to the *n*-type except that in operation all battery polarities are reversed.

Fig.2 shows the structure of a junction transistor of the *n-p-n* type. It is composed of a wafer of *p*-type germanium between two smaller layers of *n*-type germanium. Low-resistance connections are made to the *n*-layers, one of which serves as the emitter and the other as the collector. A third low-resistance connection to the *p*-layer is the base connection. The complete assembly is encased in plastic to provide ruggedness and freedom from atmospheric contaminants.



92CS-7968

Fig.2 - Diagrammatic Sketch Showing Structural Arrangement of Type 2N35 with Associated Simple Circuit. For Illustration Purposes, the Crystal Assembly is Rotated 90° Within the Plastic Case.



## TRANSISTORS

The principle of operation of the junction transistor is somewhat different from that of the point-contact transistor. In the  $n-p-n$  junction transistor, electrons from the  $n$ -layer diffuse through the  $p$ -layer and are attracted to the collector. The  $p$ -layer has a surplus of holes. Because the  $p$ -layer is very thin, most of the electrons entering the base region from the emitter will reach the collector region without recombining (neutralizing) the holes. Practically all of the electrons leaving the emitter reach the collector, thus resulting in a current amplification factor approaching unity.

The action of the  $p-n-p$  type of junction transistor is similar to that of the  $n-p-n$  type except that the polarities of the battery voltages are reversed and conduction is caused by holes instead of electrons.

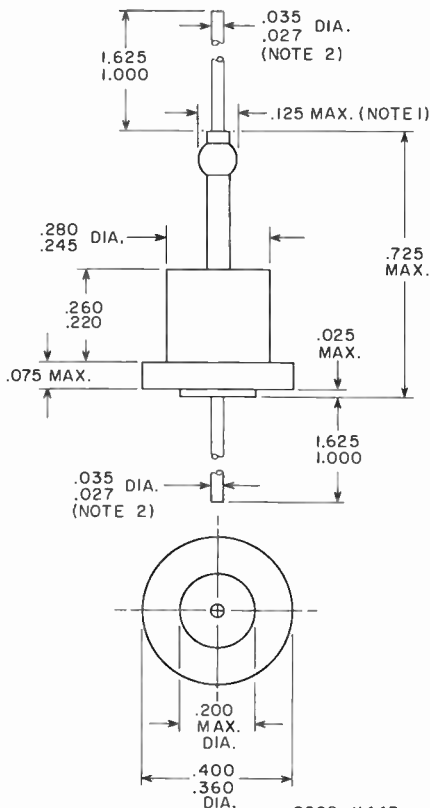
Transistors are essentially low-impedance devices, that is, they deal with current changes rather than voltage changes. They are small in size and the power requirements for their operation are extremely small. In addition, they operate instantaneously on application of voltages to the electrodes.

The point-contact transistor has a current amplification factor greater than unity. This feature contributes to its usefulness in oscillator and triggering applications. In addition, the point-contact transistor can be operated at relatively high frequencies. Because of this feature, it has considerable application in switching circuits and in radio circuits such as intermediate-frequency amplifiers, radio-frequency amplifiers, and radio-frequency oscillators.

The junction transistor has a current amplification factor approaching unity. This characteristic contributes to the stability of the junction transistor even under short-circuit conditions. It has a high operating power gain and can operate with extremely low values of input power — features which are of primary importance in oscillator and amplifier applications in the audio-frequency and low-frequency ranges.

# Outline DO-1

JEDEC No. DO-1  
All Dimensions in Inches



92CS-II443

NOTE 1: DIMENSION TO ALLOW FOR PINCH OR SEAL DEFORMATION ANYWHERE ALONG TABULATION (OPTIONAL).

NOTE 2: DIMENSION TO BE CONTROLLED FROM FREE END OF LEAD TO WITHIN 0.188 INCH FROM THE POINT OF ATTACHMENT TO THE BODY. WITHIN THE 0.188 INCH DIMENSION, THE DIAMETER MAY VARY TO ALLOW FOR LEAD FINISHES AND IRREGULARITIES.



RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division

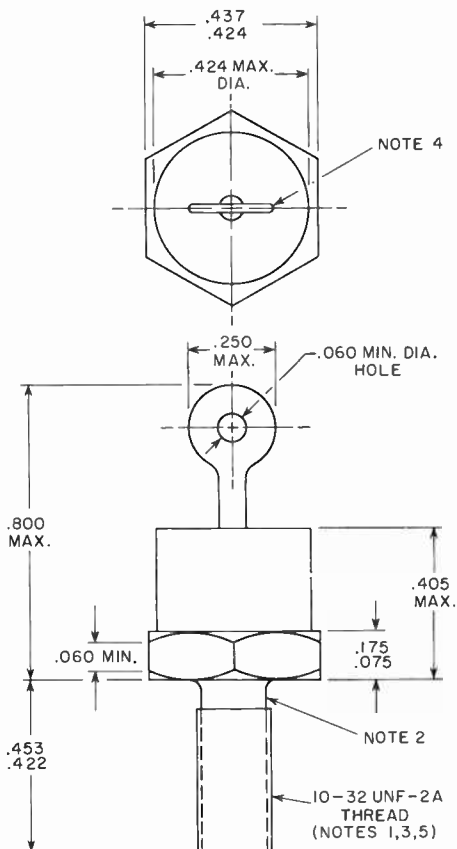
Somerville, N. J.

OUTLINE DO-1

2-62

# Outline DO-4

JEDEC No. DO-4  
All Dimensions in Inches



92CS-11446

NOTE 1: UNIT MUST NOT BE DAMAGED BY TORQUE OF 15 INCH-POUNDS APPLIED TO 10-32 UNF-2B NUT ASSEMBLED ON THREAD.

NOTE 2: DIAMETER OF UNTHREADED PORTION D.189 INCH MAXIMUM, D.163 INCH MINIMUM.

NOTE 3: COMPLETE THREADS TO EXTEND TO WITHIN 2-1/2 THREADS OF HEAD.

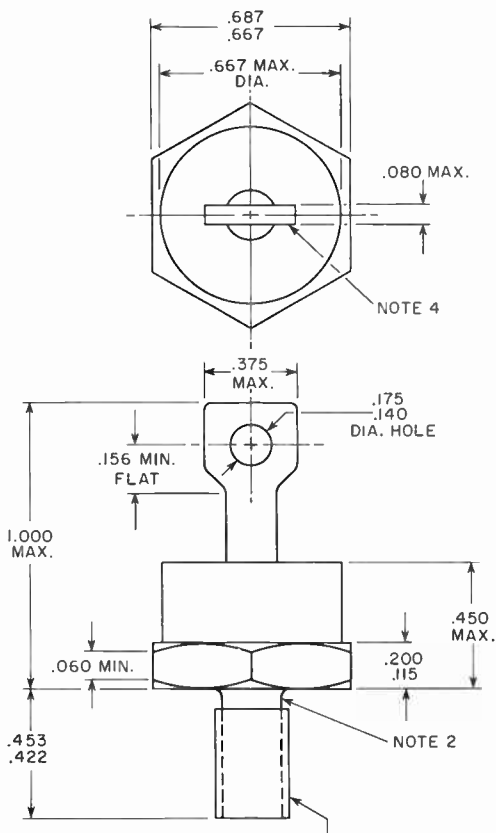
NOTE 4: ANGULAR ORIENTATION OF THIS TERMINAL IS UNDEFINED.

NOTE 5: MAXIMUM PITCH DIAMETER OF PLATED THREADS SHALL BE BASIC PITCH DIAMETER (0.1697 INCH) REFERENCE (SCREW THREAD STANDARDS FOR FEDERAL SERVICES, 1957) HANDBOOK H28 1957 PL.



# Outline DO-5

JEDEC No. DO-5  
All Dimensions in Inches



1/4-28 UNF-2A THREAD  
(1/4-28 NF-2 THREAD OPTIONAL)  
(NOTES 1,3,5)

92CS-11448

NOTE 1: UNIT MUST NOT BE DAMAGED BY TORQUE OF 30 INCH-POUNDS APPLIED TO 1/4-28 UNF-28 NUT ASSEMBLED ON THREAD.

RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division

Somerville, N. J.



NOTE 2: DIAMETER OF UNTHREADED PORTION 0.249 INCH MAXIMUM,  
0.220 INCH MINIMUM.

NOTE 3: COMPLETE THREADS TO EXTEND TO WITHIN 2-1/2 THREADS  
OF HEAD.

NOTE 4: ANGULAR ORIENTATION OF THIS TERMINAL IS UNDEFINED.

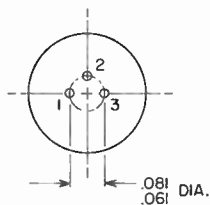
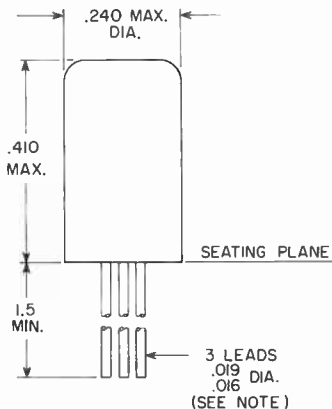
NOTE 5: MAXIMUM PITCH DIAMETER OF PLATED THREADS SHALL BE  
BASIC PITCH DIAMETER (0.2268 INCH) REFERENCE (SCREW THREAD  
STANDARDS FOR FEDERAL SERVICES, 1957) HANDBOOK H28 1957 PL.







JEDEC No. TO-1  
All Dimensions in Inches



92CS-11449

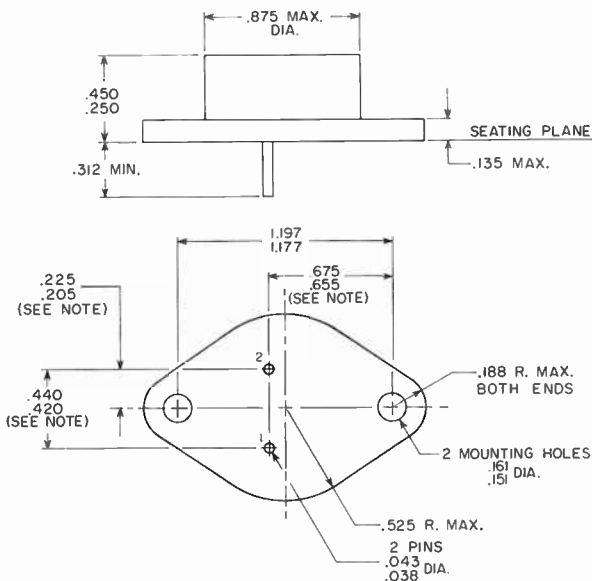
NOTE: THE SPECIFIED LEAD DIAMETER APPLIES IN ZONE BETWEEN 0.050 INCH AND 0.250 INCH FROM THE SEATING PLANE. BETWEEN 0.250 INCH AND 1.5 INCHES, A MAXIMUM DIAMETER OF 0.021 INCH IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.



# Outline TO-3

JEDEC No. TO-3

All Dimensions in Inches

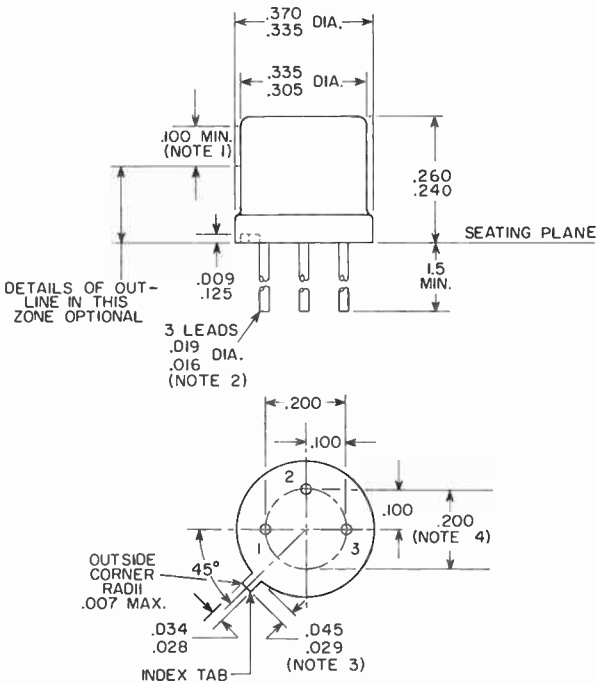


92CS-11455

NOTE: THESE DIMENSIONS SHOULD BE MEASURED AT POINTS 0.050 INCH TO 0.055 INCH BELOW SEATING PLANE. WHEN GAUGE IS NOT USED, MEASUREMENT WILL BE MADE AT SEATING PLANE.

JEDEC No. TO-5

All Dimensions in Inches



92CS-11444

THIS DEVICE IS FOR SOCKETED, SINGLE-SIDED-CIRCUIT BOARD, WIRE-IN AND SIMILAR APPLICATIONS. WHERE USED IN DOUBLE-SIDED OR EYELETED-CIRCUIT BOARD, OR SIMILAR APPLICATIONS WHERE SOLDER BRIDGING MAY OCCUR, A DIELECTRIC WASHER OR OTHER STANO-OFF DEVICE MAY BE NECESSARY.

**NOTE 1:** THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE VARIATION IN ACTUAL DIAMETER WITHIN THE ZONE SHALL NOT EXCEED 0.010 INCH.

**NOTE 2:** THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.050 INCH AND 0.250 INCH FROM THE SEATING PLANE. BETWEEN 0.250 INCH AND 1.5 INCHES, A MAXIMUM DIAMETER OF 0.021 INCH IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.



# Outline TO-5

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NOTE 3: MEASURED FROM MAXIMUM DIAMETER OF THE ACTUAL DEVICE.

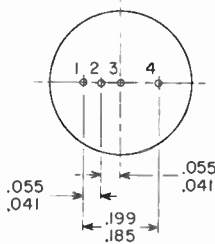
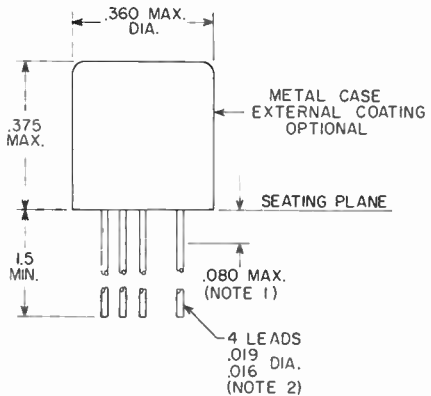
NOTE 4: LEADS HAVING MAXIMUM DIAMETER (0.019 INCH) MEASURED IN GAUGING PLANE 0.054 INCH +0.001 INCH - 0.000 INCH BELOW THE SEATING PLANE OF THE DEVICE SHALL BE WITHIN 0.007 INCH OF THEIR TRUE LOCATIONS RELATIVE TO A MAXIMUM-WIDTH TAB.

NOTE 5: THE DEVICE MAY BE MEASURED BY DIRECT METHODS OR BY THE GAUGE AND GAUGING PROCEDURE DESCRIBED ON THE SHEET "GAUGE GS-1."



# Outline TO-7

JEDEC No. TO-7  
All Dimensions in Inches



92CS-11447

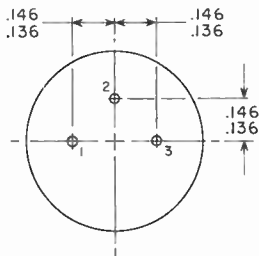
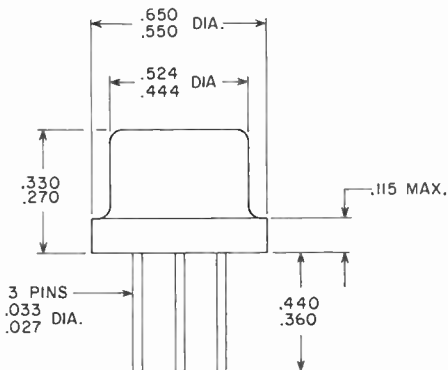
NOTE 1: EXTERNALLY COATED DEVICES SHALL NOT HAVE COATING ON THE LEADS BEYOND THIS ZONE.

NOTE 2: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN  $0.050$  INCH AND  $0.250$  INCH FROM THE SEATING PLANE. BETWEEN  $0.250$  INCH AND  $1.5$  INCHES, A MAXIMUM DIAMETER OF  $0.021$  INCH IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.



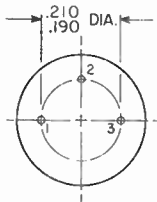
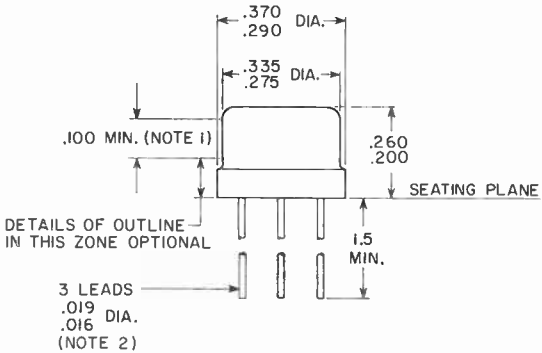
# Outline TO-8

JEDEC No. TO-8  
All Dimensions in Inches



92CS-11442

JEDEC No. TO-9  
All Dimensions in Inches



92CS-11445

THIS DEVICE IS FOR SOCKETED, SINGLE-SIDED-CIRCUIT BOARD, WIRE-IN AND SIMILAR APPLICATIONS. WHERE USED IN DOUBLE-SIDED OR EYELETED-CIRCUIT BOARD, OR SIMILAR APPLICATIONS WHERE SOLDER BRIDGING MAY OCCUR, A DIELECTRIC WASHER OR OTHER STAND-OFF DEVICE MAY BE NECESSARY.

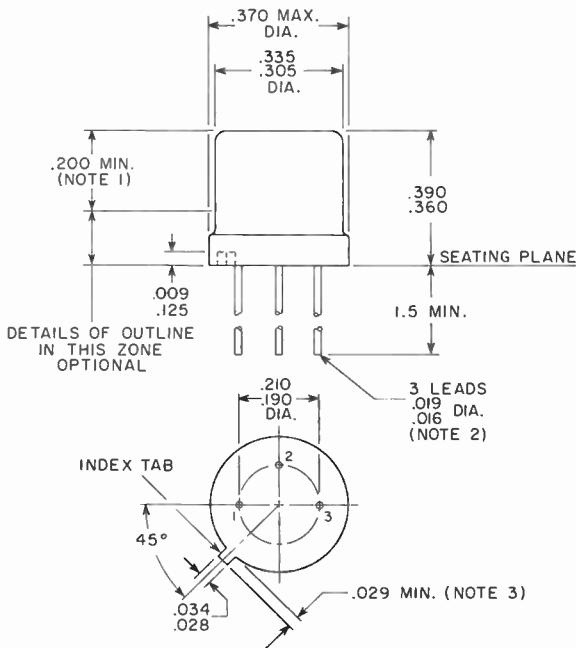
**NOTE 1:** THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE VARIATION IN ACTUAL DIAMETER WITHIN THE ZONE SHALL NOT EXCEED 0.010 INCH.

**NOTE 2:** THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.050 INCH AND 0.250 INCH FROM THE SEATING PLANE. BETWEEN 0.250 INCH AND 1.5 INCHES, A MAXIMUM DIAMETER OF 0.021 INCH IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.



# Outline TO-11

JEDEC No. TO-11  
All Dimensions in Inches



92CS-II437

THIS DEVICE IS FOR SOCKETED, SINGLE-SIDED-CIRCUIT BOARD, WIRE-IN, AND SIMILAR APPLICATIONS. WHERE USED IN DOUBLE-SIDED OR EYELETED-CIRCUIT BOARD, OR SIMILAR APPLICATIONS WHERE SOLDER BRIDGING MAY OCCUR, A DIELECTRIC WASHER OR OTHER STAND-OFF DEVICE MAY BE NECESSARY.

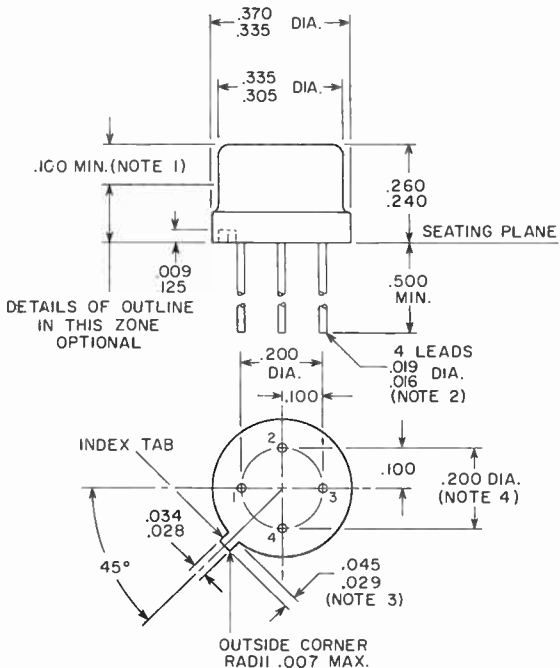
**NOTE 1:** THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE VARIATION IN ACTUAL DIAMETER WITHIN THE ZONE SHALL NOT EXCEED 0.010 INCH.

**NOTE 2:** THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.050 INCH AND 0.250 INCH FROM THE SEATING PLANE. BETWEEN 0.250 INCH AND 1.5 INCHES, A MAXIMUM DIAMETER OF 0.021 INCH IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

**NOTE 3:** MEASURED FROM MAXIMUM DIAMETER OF THE ACTUAL DEVICE.



JEDEC No. TO-12  
All Dimensions in Inches



THIS DEVICE IS FOR SOCKETED, SINGLE-SIDED-CIRCUIT BOARD, WIRE-IN AND SIMILAR APPLICATIONS. WHERE USED IN DOUBLE-SIDED OR EYELETTED-CIRCUIT BOARD, OR SIMILAR APPLICATIONS WHERE SOLDER BRIDGING MAY OCCUR, A DIELECTRIC WASHER OR OTHER STAND-OFF DEVICE MAY BE NECESSARY.

**NOTE 1:** THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE VARIATION IN ACTUAL DIAMETER WITHIN THE ZONE SHALL NOT EXCEED 0.010 INCH.

**NOTE 2:** THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.050 INCH AND 0.250 INCH FROM THE SEATING PLANE. BETWEEN 0.250 INCH AND 0.500 INCH, A MAXIMUM DIAMETER OF 0.021 INCH IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

**NOTE 3:** MEASURED FROM MAXIMUM DIAMETER OF THE ACTUAL DEVICE.



# Outline TO-12

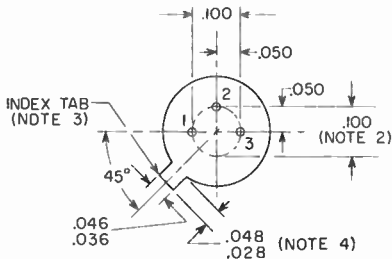
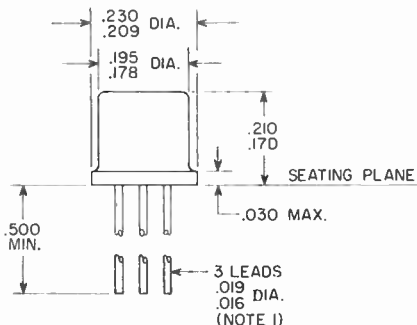
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NOTE 4: LEADS HAVING MAXIMUM DIAMETER (0.019 INCH) MEASURED IN GAUGING PLANE 0.054 INCH + 0.001 INCH - 0.000 INCH BELOW THE SEATING PLANE OF THE DEVICE SHALL BE WITHIN 0.007 INCH OF THEIR TRUE LOCATIONS RELATIVE TO A MAXIMUM-WIDTH TAB.

NOTE 5: THE DEVICE MAY BE MEASURED BY DIRECT METHODS OR BY THE GAUGE AND GAUGING PROCEDURE DESCRIBED ON THE SHEET "GAUGE GS-1."



JEDEC No. TO-18  
All Dimensions in Inches



92CS-11456

**NOTE 1:** THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.050 INCH AND 0.250 INCH FROM THE SEATING PLANE. BETWEEN 0.250 INCH AND THE END OF THE LEAD, A MAXIMUM DIAMETER OF 0.021 INCH IS HELD. OUTSIDE THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

**NOTE 2:** LEADS HAVING MAXIMUM DIAMETER (0.019 INCH) MEASURED IN GAUGING PLANE 0.054 INCH + 0.001 INCH - 0.000 INCH BELOW THE SEATING PLANE OF THE DEVICE SHALL BE WITHIN 0.007 INCH OF THEIR TRUE LOCATIONS RELATIVE TO A MAXIMUM-WIDTH TAB AND TO THE MAXIMUM 0.230 INCH DIAMETER MEASURED WITH A SUITABLE GAUGE. WHEN GAUGE IS NOT USED, MEASUREMENT WILL BE MADE AT SEATING PLANE.

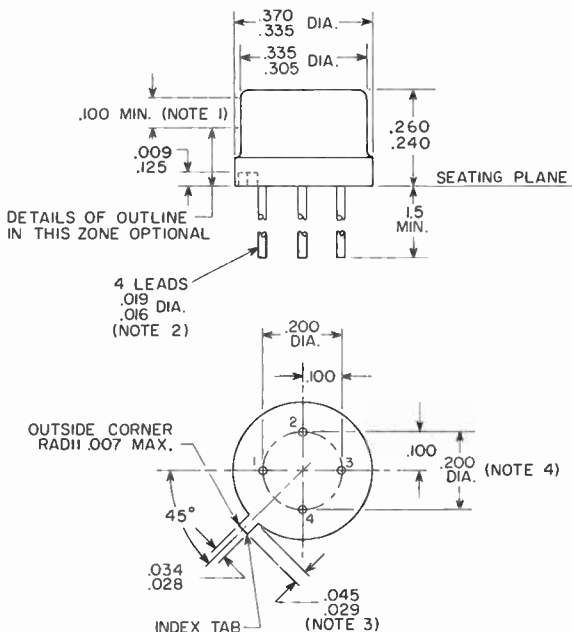
**NOTE 3:** INDEX TAB FOR VISUAL ORIENTATION ONLY.

**NOTE 4:** MEASURED FROM MAXIMUM DIAMETER OF ACTUAL DEVICE.



# Outline TO-33

JEDEC No. TO-33  
All Dimensions in Inches



92CS-11457

THIS DEVICE IS FOR SOCKETED, SINGLE-SIDED-CIRCUIT BOARD, WIRE-IN AND SIMILAR APPLICATIONS. WHERE USED IN DOUBLE-SIDED OR EYELETTED-CIRCUIT BOARD, OR SIMILAR APPLICATIONS WHERE SOLDER BRIDGING MAY OCCUR, A DIELECTRIC WASHER OR OTHER STAND-OFF DEVICE MAY BE NECESSARY.

NOTE 1: THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE VARIATION IN ACTUAL DIAMETER WITHIN THE ZONE SHALL NOT EXCEED  $0.010$  INCH.

NOTE 2: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN  $0.050$  INCH AND  $0.250$  INCH FROM THE SEATING PLANE. BETWEEN  $0.250$  INCH AND  $1.5$  INCHES, A MAXIMUM DIAMETER OF  $0.021$  INCH IS HELD. OUTSIDE THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

NOTE 3: MEASURED FROM MAXIMUM DIAMETER OF THE ACTUAL DEVICE.

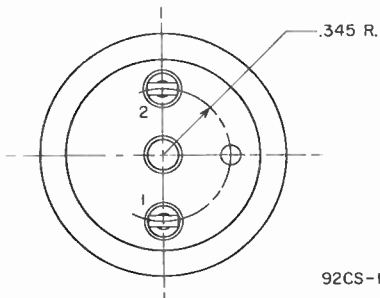
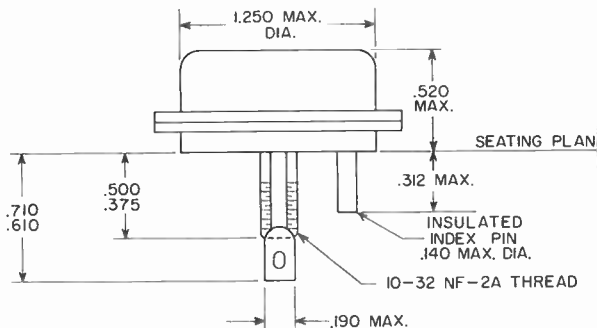
NOTE 4: LEADS HAVING MAXIMUM DIAMETER (0.019 INCH) MEASURED IN GAUGING PLANE 0.054 INCH  $\pm$  0.001 INCH - 0.000 INCH BELOW THE SEATING PLANE OF THE DEVICE SHALL BE WITHIN 0.007 INCH OF THEIR TRUE LOCATIONS RELATIVE TO A MAXIMUM-WIDTH TAB.

NOTE 5: THE DEVICE MAY BE MEASURED BY DIRECT METHODS OR BY THE GAUGE AND GAUGING PROCEDURE DESCRIBED ON THE SHEET "GAUGE GS-1."



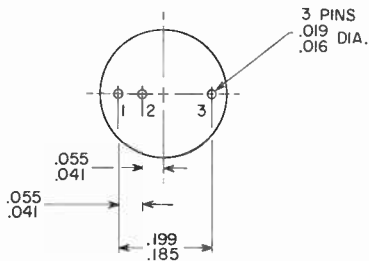
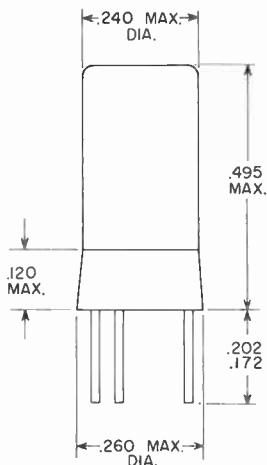
# Outline TO-36

JEDEC No. TO-36  
All Dimensions in Inches



# Outline TO-40

JEDEC No. TO-40  
All Dimensions in Inches



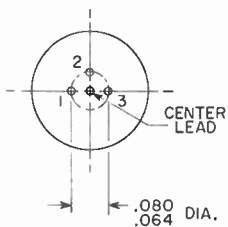
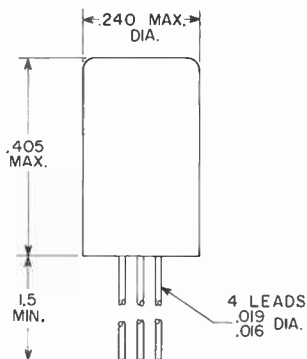
92CS-11451



# Outline TO-44

JEDEC No. TO-44

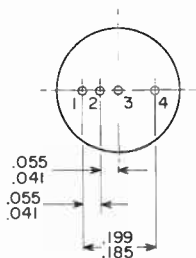
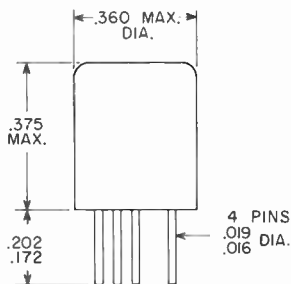
All Dimensions in Inches



92CS-11452



JEDEC No. TO-45  
All Dimensions in Inches



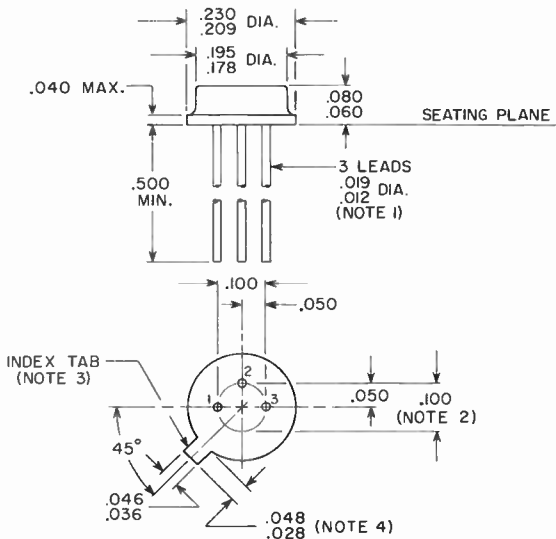
92CS-11453



# Outline TO-46

JEDEC No. TO-46

All Dimensions in Inches



92CS-11438

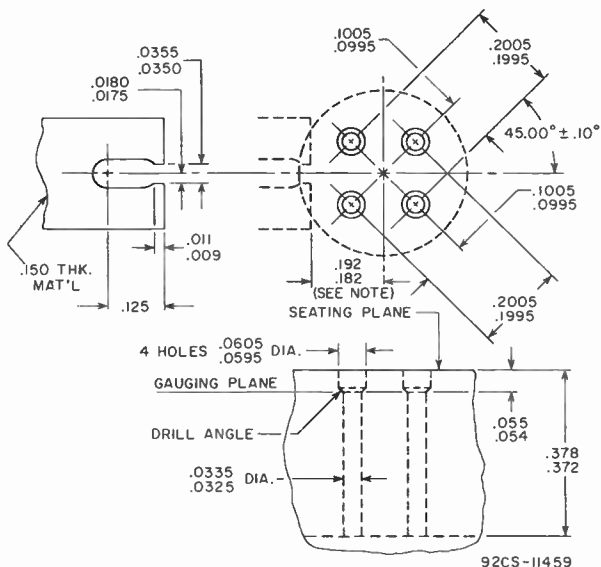
**NOTE 1:** THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.050 INCH AND 0.250 INCH FROM THE SEATING PLANE. BETWEEN 0.250 INCH AND THE END OF THE LEAD, A MAXIMUM DIAMETER OF 0.021 INCH IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

**NOTE 2:** LEADS HAVING MAXIMUM DIAMETER (0.019 INCH) MEASURED IN GAUGING PLANE  $0.054 \text{ INCH} + 0.001 \text{ INCH} - 0.000 \text{ INCH}$  BELOW THE SEATING PLANE OF THE DEVICE SHALL BE WITHIN 0.007 INCH OF THEIR TRUE LOCATIONS RELATIVE TO A MAXIMUM-WIDTH TAB AND TO THE MAXIMUM 0.230 INCH DIAMETER MEASURED WITH A SUITABLE GAUGE. WHEN GAUGE IS NOT USED, MEASUREMENT WILL BE MADE AT SEATING PLANE.

**NOTE 3:** INDEX TAB FOR VISUAL ORIENTATION ONLY.

**NOTE 4:** MEASURED FROM MAXIMUM DIAMETER OF ACTUAL DEVICE.

JEDEC No. GS-1  
All Dimensions in Inches



NOTE: THE LOCATION OF THE TAB LOCATOR WITHIN THE LIMITS INDICATED WILL BE DETERMINED BY THE TAB AND FLANGE DIMENSION OF THE DEVICE BEING CHECKED.

THE FOLLOWING GAUGING PROCEDURE SHALL BE USED:

THE DEVICE BEING MEASURED SHALL BE INSERTED UNTIL ITS SEATING PLANE IS 0.125 INCH ± 0.010 INCH FROM THE SEATING SURFACE OF THE GAUGE. A FORCE OF 8.0 ± 0.5 OZ. SHALL THEN BE APPLIED PARALLEL AND SYMMETRICAL TO THE DEVICE'S CYLINDRICAL AXIS. WHEN EXAMINED VISUALLY AFTER THE FORCE APPLICATION (THE FORCE NEED NOT BE REMOVED) THE SEATING PLANE OF THE DEVICE SHALL BE SEATED AGAINST THE GAUGE.

THE USE OF A PIN STRAIGHTENER PRIOR TO INSERTION IN THE GAUGE IS PERMISSIBLE.

A SPACER MAY BE USED TO OBTAIN THE 0.125 INCH DISTANCE FROM THE GAUGE SEAT PRIOR TO FORCE APPLICATION.

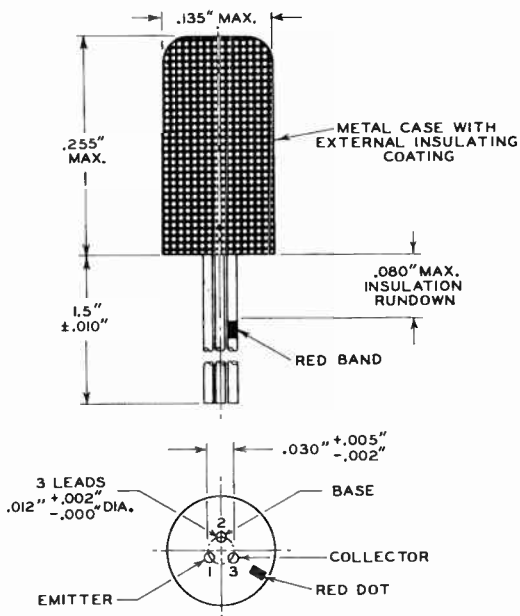






# OUTLINES

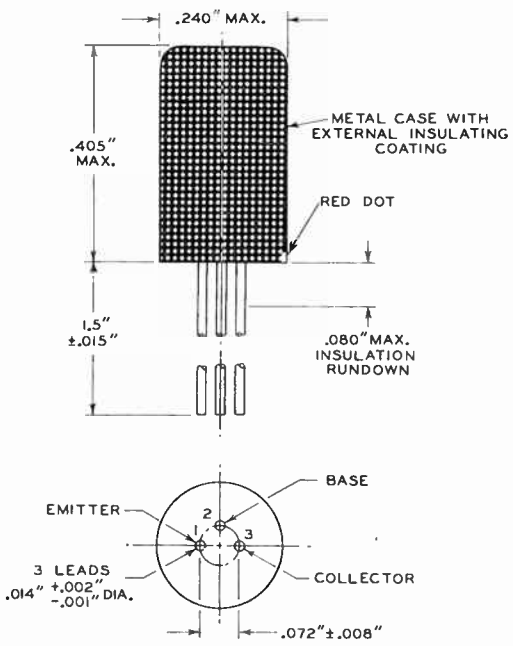
SEMICONDUCTOR DEVICES  
FLEXIBLE LEAD TYPE





# OUTLINES

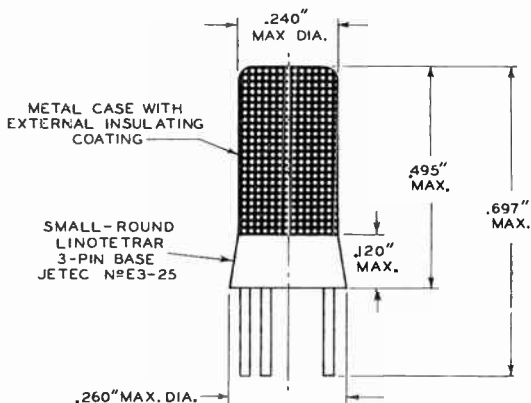
SEMICONDUCTOR DEVICES  
FLEXIBLE LEAD TYPE





# OUTLINES

SEMICONDUCTOR DEVICES  
LINOTETRAR--Linotetrar 3-Pin Base Types





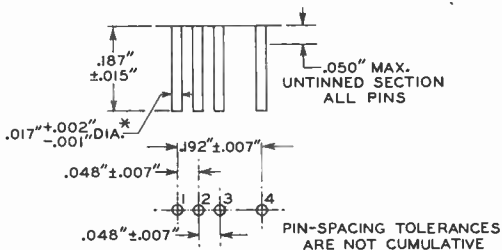




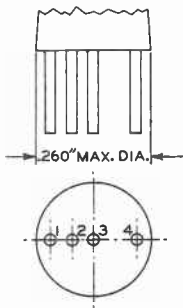
# BASES

SEMICONDUCTOR DEVICES

## "LINOTETRAR" PIN DIMENSIONS AND ORIENTATION



## SMALL-ROUND LINOTETRAR



No. of Pins	Pins	JETEC No.	RCA No.
4-Pin	1, 2, 3, 4	E4-24	-
3-Pin	1, 2, 4	E3-25	-

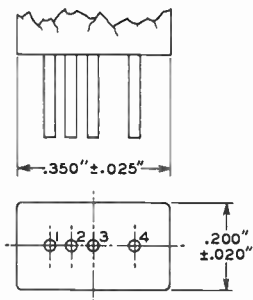
\* The specified pin diameter applies only in the zone between 0.050" from the base seat and the end of the pin.



# BASES

SEMICONDUCTOR DEVICES

## SMALL-RECTANGLE LINOTETRAR



<i>No. of Pins</i>	<i>Pins</i>	<i>JETEC No.</i>	<i>RCA No.</i>
4-Pin	1, 2, 3, 4	E4-31	-
3-Pin	1, 2, 4	E3-32	-
2-Pin	1, 4	E2-33	FS6151

*For other dimensions, see first page of the "Linotetrar" series*



IN34-A

# IN34-A

## SEMICONDUCTOR DIODE

GERMANIUM POINT-CONTACT TYPE

*A general-purpose type intended for low-power rectification in applications such as isolating, clipping, and switching circuits, as well as in certain meter circuits*

### DATA

#### General:

Maximum Envelope Length (Including studs) . . . . .	7/8"	←
Maximum Envelope Diameter . . . . .	1/4"	
Maximum Overall Length (Including flexible leads). . . . .	4-1/8"	←
Leads, Flexible . . . . .	2	
Length. . . . .	1-3/8" to 1-5/8"	
Diameter. . . . .	0.029" to 0.032"	←
Envelope, Glass . . . . .	T-1-1/3	
Operating Position. . . . .	Any	

### RECTIFIER SERVICE

*For power-supply frequency of 25 cps and above*

#### Maximum Ratings, Absolute Values:

PEAK INVERSE VOLTAGE. . . . .	60 max.	volts
FORWARD CURRENT:		
Peak. . . . .	150 max.	ma
Average*. . . . .	50 max.	ma
Fault, for duration of 0.1 second max .	500 max.	ma
AMBIENT-TEMPERATURE RANGE . . . . .	-55 to +75	°C

#### Characteristics, At Ambient Temperature of 25°C:

Minimum Forward Current at dc volts = 1 .	5	ma
Maximum Average Inverse Current:		
At dc volts = -10 . . . . .	30	μamp
At dc volts = -50 . . . . .	500	μamp
Minimum Peak Inverse Voltage for zero dynamic resistance . . . . .	75	volts
Capacitance Between Stud Tips (Approx.) . . . . .	1	μf

\* Averaged over one conduction cycle.

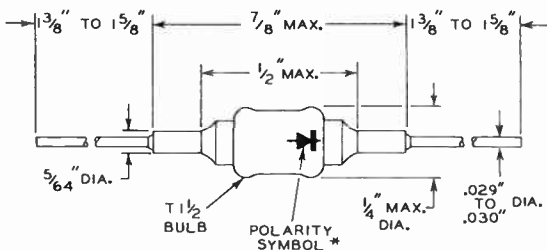
← indicates a change.

IN34-A



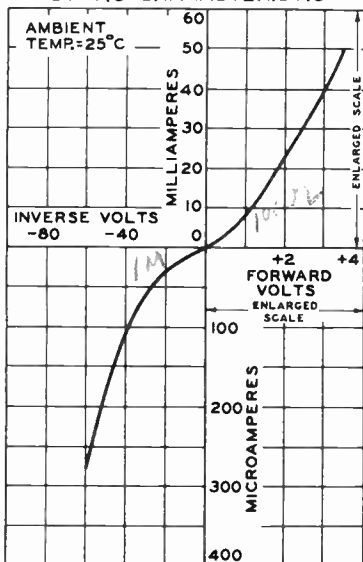
IN34-A

SEMICONDUCTOR DIODE



\*ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT AS INDICATED BY DC AMMETER.  
92CS-7980R1

STATIC CHARACTERISTIC



92CS-7976T



IN38-A

# IN38-A

## SEMICONDUCTOR DIODE

GERMANIUM POINT-CONTACT TYPE

*A large-signal type having a high peak inverse voltage rating and intended for use in electronic computers and clamping circuits*

### DATA

#### General:

Maximum Envelope Length (Including studs) . . . . .	7/8"	←
Maximum Envelope Diameter . . . . .	1/4"	
Maximum Overall Length (Including flexible leads) . . . . .	4-1/8"	←
Leads, Flexible . . . . .	2	
Length . . . . .	1-3/8" to 1-5/8"	
Diameter . . . . .	0.029" to 0.032"	←
Envelope, Glass . . . . .	T-1-1/2	
Operating Position . . . . .	Any	

### RECTIFIER SERVICE

*For power-supply frequency of 25 cps and above*

#### Maximum Ratings, Absolute Values:

PEAK INVERSE VOLTAGE . . . . .	100 max.	volts
FORWARD CURRENT:		
Peak . . . . .	150 max.	ma
Average* . . . . .	50 max.	ma
Fault, for duration of 0.1 second max. . . . .	500 max.	ma
AMBIENT-TEMPERATURE RANGE . . . . .	-50 to +75	°C

#### Characteristics, At Ambient Temperature of 25°C:

Minimum Forward Current at dc volts = 1 . . . . .	4	ma
Maximum Average Inverse Current:		
At dc volts = -3 . . . . .	5	μamp
At dc volts = -100 . . . . .	500	μamp
Minimum Peak Inverse Voltage for zero dynamic resistance . . . . .	120	volts
Capacitance Between Stud Tips (Approx.) . . . . .	1	μmf

\* Averaged over one conduction cycle.

← Indicates a change.

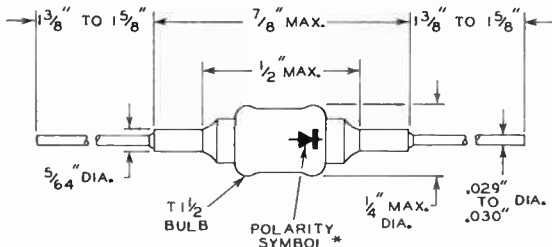


IN38-A



IN38-A

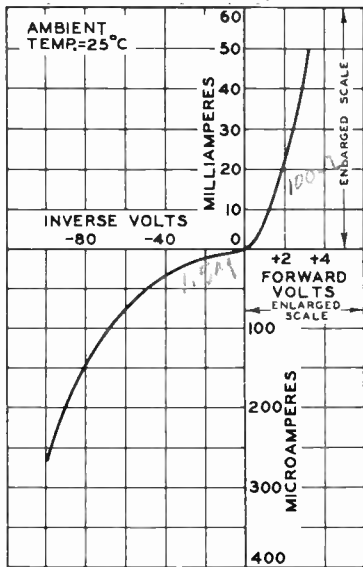
SEMICONDUCTOR DIODE



\*ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT AS INDICATED BY DC AMMETER.

92CS-7980R1

STATIC CHARACTERISTIC



92CS-8022T



IN54-A

# IN54-A

## SEMICONDUCTOR DIODE

GERMANIUM POINT-CONTACT TYPE

*A high-back-resistance type intended for use in clipping circuits, high-impedance high-voltage probes, dc restorer circuits, and high-impedance detector circuits*

### DATA

#### General:

Maximum Envelope Length (Including studs) . . . . .	7/8"	←
Maximum Envelope Diameter . . . . .	1/4"	
Maximum Overall Length (Including flexible leads). . . . .	4-1/8"	←
Leads, Flexible . . . . .	2"	
Length. . . . .	1-3/8" to 1-5/8"	
Diameter. . . . .	0.029" to 0.032"	←
Envelope, Glass . . . . .	T-1-1/2"	
Operating Position. . . . .	Any	

### RECTIFIER SERVICE

*For power-supply frequency of 25 cps and above*

#### Maximum Ratings, Absolute Values:

PEAK INVERSE VOLTAGE. . . . .	50 max.	volts
FORWARD CURRENT:		
Peak. . . . .	150 max.	ma
Average*. . . . .	50 max.	ma
Fault, for duration of 0.1 second max . .	500 max.	ma
AMBIENT-TEMPERATURE RANGE . . . . .	-50 to +75	°C

#### Characteristics, At Ambient Temperature of 25°C:

Minimum Forward Current at dc volts = 1 . . . . .	5	ma
Maximum Average Inverse Current:		
At dc volts = -10 . . . . .	7	μamp
At dc volts = -50 . . . . .	100	μamp
Minimum Peak Inverse Voltage for zero dynamic resistance . . . . .	75	volts
Capacitance Between Stud Tips (Approx.) . . . . .	1	μf

\* Averaged over one conduction cycle.

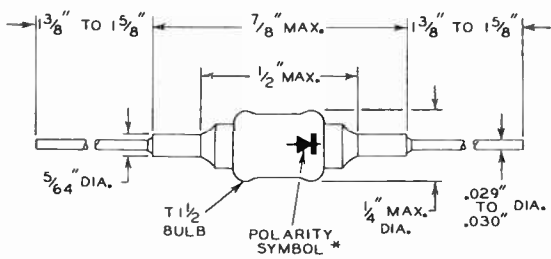
← indicates a change.



IN54-A

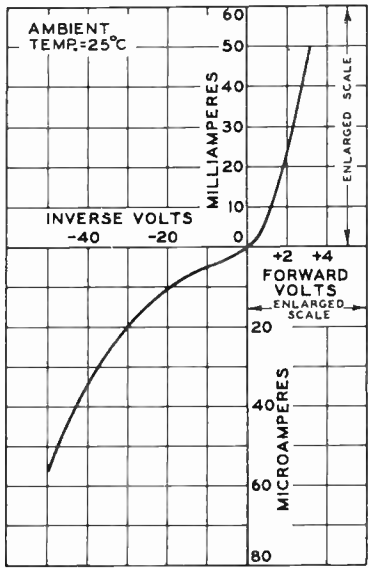
IN54-A

SEMICONDUCTOR DIODE



\*ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT AS INDICATED BY DC AMMETER.  
92CS-7980R1

STATIC CHARACTERISTIC



92CS-8021T





1N55-A

1N55-A

### CRYSTAL DIODE

GERMANIUM POINT-CONTACT TYPE

*A large-signal type having a high peak inverse voltage rating and intended for use in electronic computers, clamping circuits, dc restorer circuits, and in high-voltage probes.*

#### DATA

##### General:

Maximum Envelope Length (Including studs) . . . . .	15/16"
Maximum Envelope Diameter . . . . .	1/4"
Maximum Overall Length (Including flexible leads) . . . . .	4-3/16"
Leads, Flexible . . . . .	2
Length . . . . .	1-3/8" to 1-5/8"
Diameter . . . . .	0.025"
Envelope, Glass . . . . .	T-1-1/2
Operating Position . . . . .	Any

#### RECTIFIER SERVICE

*For frequencies of 25 cps and above*

##### Maximum Ratings, Absolute Values:

PEAK INVERSE VOLTAGE . . . . .	150 max.	volts
FORWARD CURRENT:		
Peak . . . . .	150 max.	ma
Average* . . . . .	50 max.	ma
FAULT CURRENT <sup>▲</sup> (For duration of 1 sec. max.) . . . . .	500 max.	ma
AMBIENT TEMPERATURE RANGE . . . . .	-50 to +75	°C

##### Characteristics at Ambient Temperature of 25°C:

Minimum Forward Current at dc volts = 1 . . . . .	4	ma
Maximum Average Inverse Current:		
At dc volts = -150 . . . . .	500	μamp
Minimum Peak Inverse Voltage for zero dynamic resistance . . . . .	170	volts
Shunt Capacitance (Approx.)- Measured Between Studs . . . . .	1	μuf

\* Averaged over one conduction cycle.

<sup>▲</sup> Maximum fault current is the highest value of current that should be permitted to flow through the diode under a fault condition such as load short circuit.

#### DIMENSIONAL OUTLINE

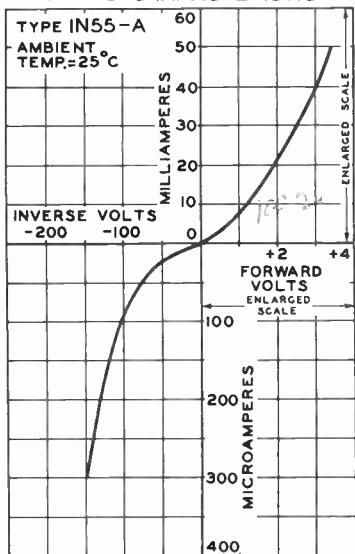
for Type 1N55-A is the same as that shown for Type 1N34-A

IN55-A



# IN55-A CRYSTAL DIODE

## STATIC CHARACTERISTIC



92CS-7977T

AUG. 1, 1953

TUBE DEPARTMENT  
RADIO CORPORATION OF AMERICA, HARRISON, NEW JERSEY

CE-7977T

World Radio History



# 1N56-A

## CRYSTAL DIODE

GERMANIUM POINT-CONTACT TYPE

*A high-conduction type featuring exceptionally low dynamic impedance and intended for limiter service in FM receivers.*

1N56-A

### DATA

#### General:

Maximum Envelope Length (including studs) . . . . .	15/16"
Maximum Envelope Diameter . . . . .	1/4"
Maximum Overall Length (including flexible leads) . . . . .	4-3/16"
Leads, Flexible . . . . .	2
Length . . . . .	1-3/8" to 1-5/8"
Diameter . . . . .	0.025"
Envelope, Glass . . . . .	T-1-1/2
Operating Position . . . . .	Any

### RECTIFIER SERVICE

*For frequencies of 25 cps and above*

#### Maximum Ratings, Absolute Values:

PEAK INVERSE VOLTAGE . . . . .	40 max.	volts
FORWARD CURRENT:		
Peak . . . . .	200 max.	ma
Average* . . . . .	60 max.	ma
FAULT CURRENT <sup>▲</sup> (For duration of 1 sec. max.) . . . . .	1000 max.	ma
AMBIENT TEMPERATURE RANGE . . . . .	-50 to +75	°C

#### Characteristics at Ambient Temperature of 25°C:

Minimum Forward Current at dc volts = 1 . . . . .	15	ma
Maximum Average Inverse Current:		
At dc volts = -30 . . . . .	300	μamp
Minimum Peak Inverse Voltage for zero dynamic resistance . . . . .	50	volts
Snunt Capacitance (Approx.) - Measured Between Studs) . . . . .	1	μf

\* Averaged over one conduction cycle.

▲ Maximum fault current is the highest value of current that should be permitted to flow through the diode under a fault condition such as load short circuit.

### DIMENSIONAL OUTLINE

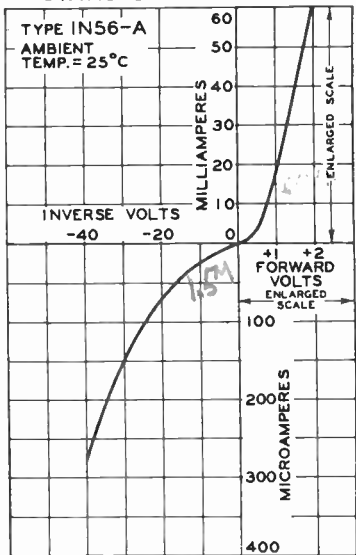
for Type 1N56-A is the same as that shown for Type 1N34-A

IN56-A



# IN56-A CRYSTAL DIODE

## STATIC CHARACTERISTIC



92CS-7978T



IN58-A

IN58-A

## SEMICONDUCTOR DIODE

GERMANIUM POINT-CONTACT TYPE

*A large-signal type having a high peak inverse voltage rating and intended for use in electronic computers and clamping circuits*

## DATA

## General:

Maximum Envelope Length (Including studs) . . . . .	7/8"	←
Maximum Envelope Diameter . . . . .	1/4"	
Maximum Overall Length (including flexible leads) . . . . .	4-1/8"	←
Leads, Flexible . . . . .	2	
Length . . . . .	1-3/8" to 1-5/8"	
Diameter . . . . .	0.029" to 0.032"	←
Envelope, Glass . . . . .	T-1-1/2	
Operating Position . . . . .	. Any	

## RECTIFIER SERVICE

*For power-supply frequency of 25 cps and above*

## Maximum Ratings, Absolute Values:

PEAK INVERSE VOLTAGE . . . . .	100 max.	volts
FORWARD CURRENT:		
Peak . . . . .	150 max.	ma
Average . . . . .	50 max.	ma
Fault, for duration of 0.1 second max. . . . .	500 max.	ma
AMBIENT-TEMPERATURE RANGE . . . . .	-50 to +75	°C

## Characteristics, At Ambient Temperature of 25°C:

Minimum Forward Current at dc volts = 1. . . . .	4	ma
Maximum Average Inverse Current at dc volts = -100 . . . . .	600	μamp
Minimum Peak Inverse Voltage for zero dynamic resistance . . . . .	120	volts
Capacitance Between Stud Tips (Approx.) . . . . .	1	μf

\* Averaged over one conduction cycle.

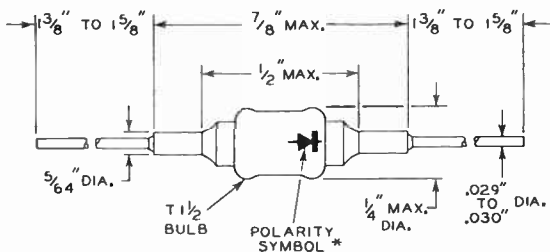
← Indicates a change.

IN58-A



IN58-A

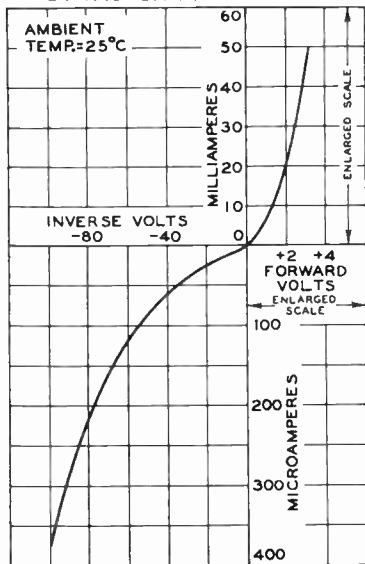
## SEMICONDUCTOR DIODE



\*ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT AS INDICATED BY DC AMMETER.

92CS-7980R1

## STATIC CHARACTERISTIC



92CS-7979T

# 1N248C, 1N248RC

## Silicon Rectifiers

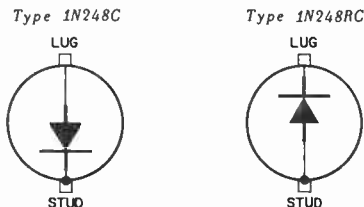
### DIFFUSED-JUNCTION TYPES

For Industrial and Military Power Supplies

### GENERAL DATA

#### Mechanical:

Operating Position. . . . . Any  
Dimensions. . . . . See *Dimensional Outline*  
Dimensional Outline. . . . . JEDEC No. D0-5  
Case. . . . . Metal  
Seals. . . . . Hermetic  
Terminal Diagrams (See *Dimensional Outline*):



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load

PEAK INVERSE VOLTAGE. . . . . 55 max. volts  
RMS SUPPLY VOLTAGE. . . . . 39 max. volts  
DC BLOCKING VOLTAGE. . . . . 50 max. volts

#### AVERAGE FORWARD CURRENT:

At case temperature of 150° C . . . . . 20 max. amp  
At other case temperatures. . . See *Average-Forward-Current Rating Chart*

PEAK RECURRENT CURRENT. . . . . 90 max. amp

#### PEAK SURGE CURRENT:<sup>a</sup>

For one-half cycle, sine wave . . . . . 350 max. amp  
For one or more cycles. . See *Peak-Surge-Current Rating Chart*

#### CASE-TEMPERATURE RANGE:

Operating and storage . . . . . -65 to +175 °C

#### Characteristics:

At case temperature of 150° C and maximum-rated voltage and average forward current

Maximum Forward Voltage Drop. . . . . 0.6 volt  
Maximum Reverse Current . . . . . 3.8 ma



# 1N248C, 1N248RC

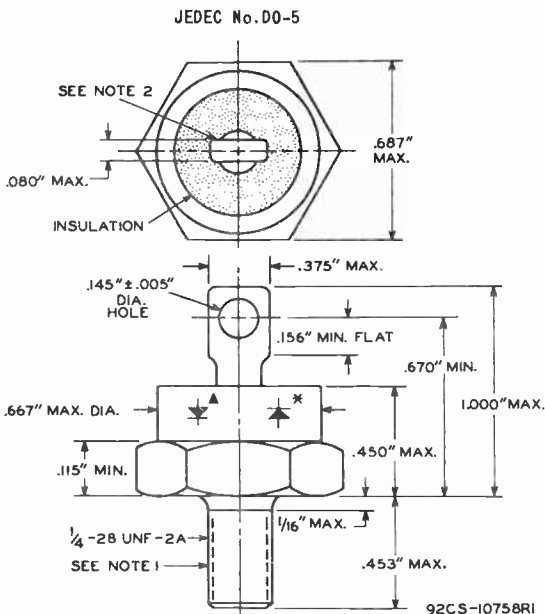
<sup>a</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

## OPERATING CONSIDERATIONS

Because these rectifiers may operate at voltages which are dangerous, care should be taken in the design of equipment to prevent the operator from coming in contact with the rectifier.

The recommended installation torque is 26 to 36 inch-pounds applied to a 1/4-2B UNF-2B hex nut assembled on stud thread.

The applied torque during installation should not exceed 75 inch-pounds.



NOTE 1: MUST WITHSTAND TORQUE OF 30 INCH-POUNDS APPLIED TO 1/4-2B UNF-2B NUT ASSEMBLED ON STUD THREAD.

NOTE 2: ANGULAR ORIENTATION OF THIS TERMINAL UNDEFINED.

<sup>▲</sup> Polarity symbol for types 1N248C, 1N249C, 1N250C, 1N1195A, 1N1196A, 1N1197A, and 1N1198A.

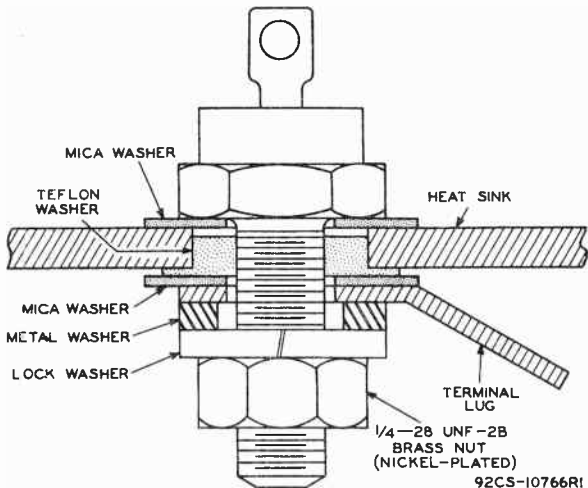
<sup>\*</sup> Polarity symbol for types 1N248RC, 1N249RC, 1N250RC, 1N1195RA, 1N1196RA, 1N1197RA, and 1N1198RA.



# 1N248C, 1N248RC

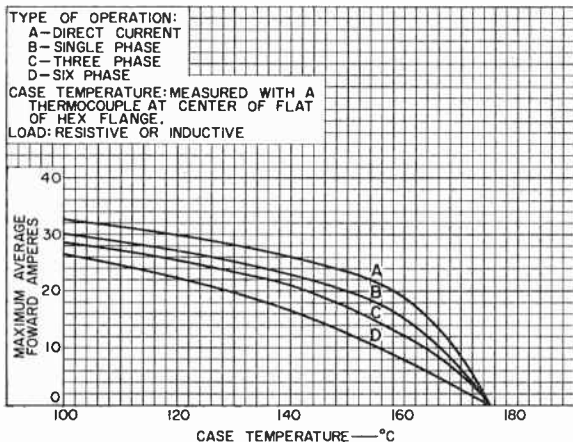
## SUGGESTED MOUNTING ARRANGEMENT

*Mounting components of the type shown are furnished with each silicon rectifier*



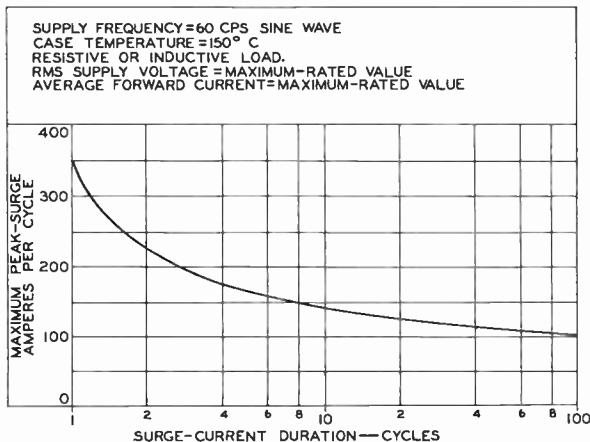
# 1N248C, 1N248RC

## AVERAGE-FORWARD-CURRENT RATING CHART



92CS-10746R1

## PEAK-SURGE-CURRENT RATING CHART

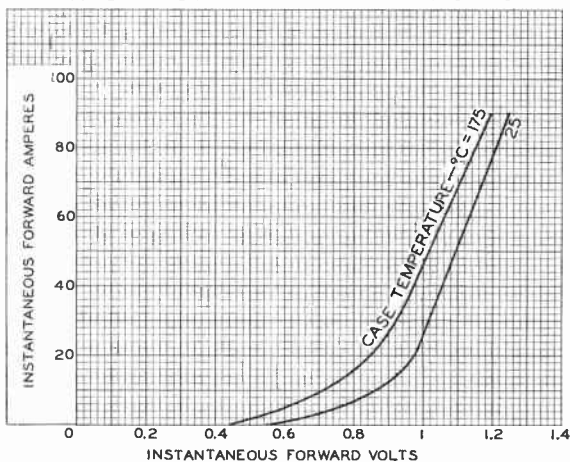


92CS-10909R1



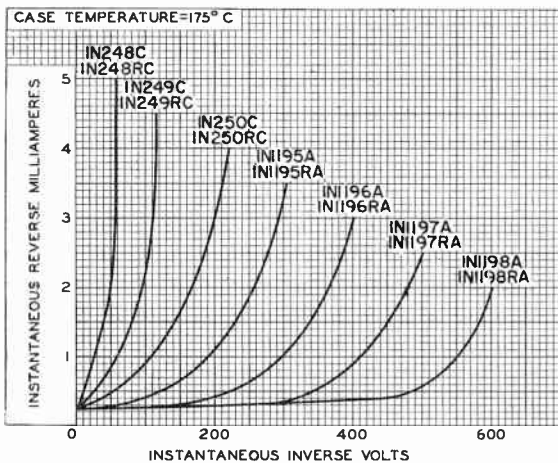
# 1N248C, 1N248RC

## TYPICAL FORWARD CHARACTERISTICS



92CS-10768

## TYPICAL REVERSE CHARACTERISTICS



92CS-10767RI





# 1N249C, 1N249RC

## Silicon Rectifiers

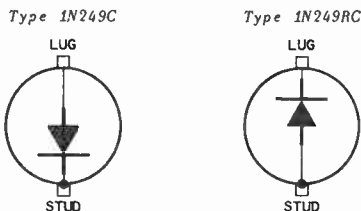
### DIFFUSED-JUNCTION TYPES

For Industrial and Military Power Supplies

#### GENERAL DATA

##### Mechanical:

Operating Position. . . . . Any  
Dimensions. . . . . See *Dimensional Outline*  
Dimensional Outline. . . . . JEDEC No. D0-5  
Case. . . . . Metal  
Seals. . . . . Hermetic  
Terminal Diagrams (See *Dimensional Outline*):



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

#### HALF-WAVE RECTIFIER

##### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load

PEAK INVERSE VOLTAGE. . . . . 110 max. volts  
RMS SUPPLY VOLTAGE. . . . . 77 max. volts  
DC BLOCKING VOLTAGE. . . . . 100 max. volts

##### AVERAGE FORWARD CURRENT:

At case temperature of 150° C . . . . . 20 max. amp  
At other case temperatures. . . See *Average-Forward-Current Rating Chart*

PEAK RECURRENT CURRENT. . . . . 90 max. amp

##### PEAK SURGE CURRENT:<sup>a</sup>

<sup>a</sup>For one-half cycle, sine wave . . . . . 350 max. amp  
For one or more cycles. . . . . See *Peak-Surge-Current Rating Chart*

##### CASE-TEMPERATURE RANGE:

Operating and storage . . . . . -65 to +175 °C

##### Characteristics:

At case temperature of 150° C and maximum-rated voltage and average forward current

Maximum Forward Voltage Drop. . . . . 0.6 volt  
Maximum Reverse Current . . . . . 3.6 ma



# 1N249C, 1N249RC

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<sup>a</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHARTS,  
and  
CURVES

shown under Types 1N248C and 1N248RC also apply to the  
1N249C and 1N249RC



# 1N250C, 1N250RC

## Silicon Rectifiers

### DIFFUSED-JUNCTION TYPES

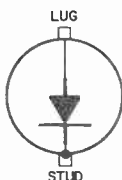
For Industrial and Military Power Supplies

#### GENERAL DATA

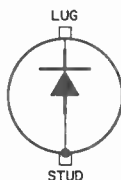
##### Mechanical:

Operating Position. . . . . Any  
Dimensions. . . . . See *Dimensional Outline*  
Dimensional Outline . . . . . JEDEC No. D0-5  
Case. . . . . Metal  
Seals . . . . . Hermetic  
Terminal Diagrams (See *Dimensional Outline*):

Type 1N250C



Type 1N250RC



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

#### HALF-WAVE RECTIFIER

##### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load

PEAK INVERSE VOLTAGE. . . . . 220 max. volts  
RMS SUPPLY VOLTAGE. . . . . 154 max. volts  
DC BLOCKING VOLTAGE . . . . . 200 max. volts

##### AVERAGE FORWARD CURRENT:

At case temperature of 150° C . . . . . 20 max. amp

At other case temperatures. . . See *Average-Forward-Current Rating Chart*

PEAK RECURRENT CURRENT. . . . . 90 max. amp

##### PEAK SURGE CURRENT:<sup>a</sup>

For one-half cycle, sine wave . . . . . 350 max. amp

For one or more cycles. . . . . See *Peak-Surge-Current Rating Chart*

##### CASE-TEMPERATURE RANGE:

Operating and storage . . . . . -65 to +175 °C

##### Characteristics:

At case temperature of 150° C and maximum-rated voltage and average forward current

Maximum Forward Voltage Drop. . . . . 0.6 volt  
Maximum Reverse Current . . . . . 3.4 ma



# 1N250C, 1N250RC

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<sup>a</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHARTS,  
and  
CURVES

shown under Types 1N248C and 1N248RC also apply to the  
1N250C and 1N250RC





# 1N1183A, 1N1183RA

## Silicon Rectifiers

### DIFFUSED-JUNCTION TYPES

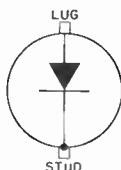
For Industrial and Military Power Supplies

### GENERAL DATA

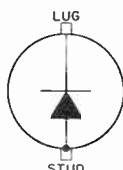
#### Mechanical:

Operating Position. . . . . Any  
Dimensions. . . . . See *Dimensional Outline*  
Dimensional Outline. . . . . JFDEC No. 00-5  
Case. . . . . Metal  
Seals. . . . . Hermetic  
Terminal Diagrams (See *Dimensional Outline*):

Type 1N1183A



Type 1N1183RA



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

Maximum and Minimum Ratings, Absolute-Maximum Values:

*For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load*

PEAK REVERSE VOLTAGE. . . . .	50 max.	volts
RMS SUPPLY VOLTAGE. . . . .	35 max.	volts
DC BLOCKING VOLTAGE. . . . .	50 max.	volts

#### AVERAGE FORWARD CURRENT:

At case temperature of 150° C . . . . .	40 max.	amp
At other case temperatures. . . . .	See <i>Average-Forward-Current Rating Chart</i>	

PEAK RECURRENT CURRENT. . . . .	195 max.	amp
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#### PEAK SURGE CURRENT:<sup>a</sup>

For one-half cycle, sine wave . . . . .	800 max.	amp
For one or more cycles. . . . .	See <i>Peak-Surge-Current Rating Chart</i>	

#### CASE-TEMPERATURE RANGE:

Operating and storage . . . . .	-65 to +200	°C
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#### Characteristics:

Maximum Forward Voltage Drop <sup>b</sup> . . . . .	0.65	volt
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#### Maximum Reverse Current:

Dynamic (Averaged over one complete cycle for maximum peak-reverse volts = 50, dc forward amperes = 40, case temperature (°C) = 150) . . . . .	2.5	ma
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# 1N1183A, 1N1183RA

Static (DC) value for maximum peak-reverse  
volts = 50, case temperature ( $^{\circ}\text{C}$ ) = 25). 0.025 ma

Maximum Thermal Resistance:

Junction-to-case. . . . . 1  $^{\circ}\text{C}/\text{watt}$

<sup>a</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>b</sup> Average value for one complete cycle, for maximum peak-reverse volts = 50, dc forward amperes = 40, case temperature ( $^{\circ}\text{C}$ ) = 150.

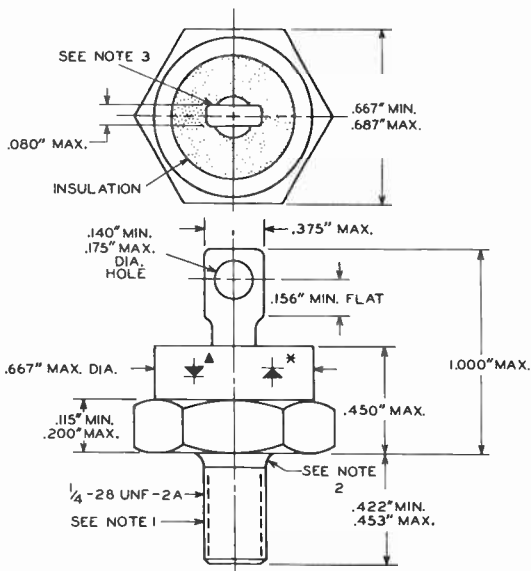
## OPERATING CONSIDERATIONS

Because these rectifiers may operate at voltages which are dangerous, care should be taken in the design of equipment to prevent the operator from coming in contact with the rectifier.

The recommended installation torque is 26 to 36 inch-pounds applied to a 1/4-28 UNF-2B hex nut assembled on stud thread.

The applied torque during installation should not exceed 50 inch-pounds.

JEDEC No. 00-5



92CS-10758R3

RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division  
Somerville, N. J.

World Radio History



# 1N1183A, 1N1183RA

NOTE 1: MUST WITHSTAND TORQUE OF 30 INCH-POUNDS APPLIED TO 1/4-28 UNF-2B NUT ASSEMBLED ON STUD THREAD.

NOTE 2: DIAMETER OF UNTHREADED PORTION: 0.249" MAXIMUM, 0.220" MINIMUM.

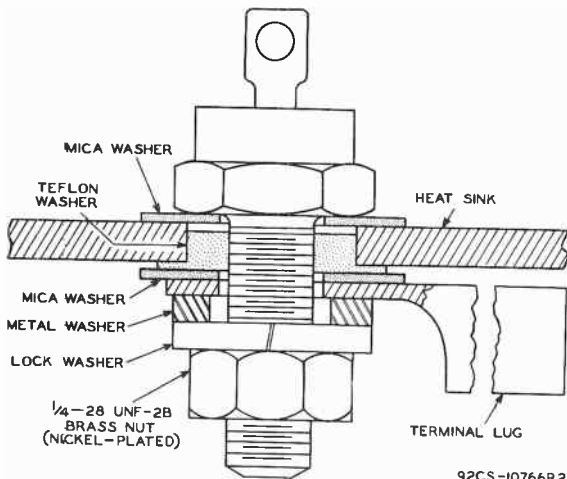
NOTE 3: ANGULAR ORIENTATION OF THIS TERMINAL UNDEFINED.

▲ Polarity symbol for types 1N1183A, 1N1184A, and 1N1186A.

\* Polarity symbol for types 1N1183RA, 1N1184RA, and 1N1186RA.

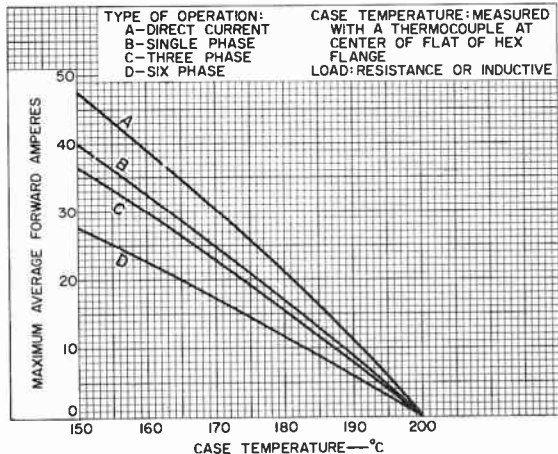
## SUGGESTED MOUNTING ARRANGEMENT

*Mounting components of the type shown are furnished with each silicon rectifier. The increase in thermal resistance with these mounting components is approximately 1.5 °C/watt.*



# 1N1183A, 1N1183RA

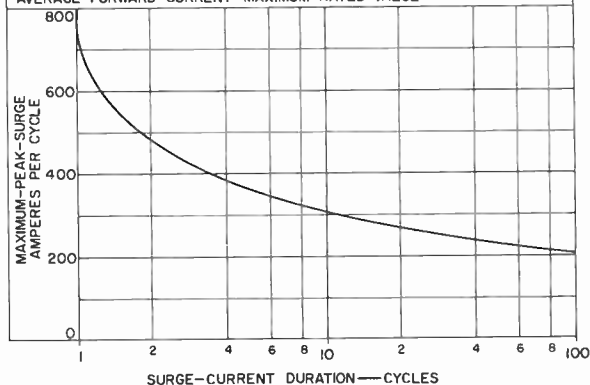
## AVERAGE-FORWARD-CURRENT RATING CHART



92CS-11343

## PEAK-SURGE-CURRENT RATING CHART

SUPPLY FREQUENCY=60 CPS SINE WAVE CASE TEMPERATURE=150° C  
RESISTIVE OR INDUCTIVE LOAD  
RMS SUPPLY VOLTAGE=MAXIMUM-RATED VALUE  
AVERAGE FORWARD CURRENT=MAXIMUM-RATED VALUE

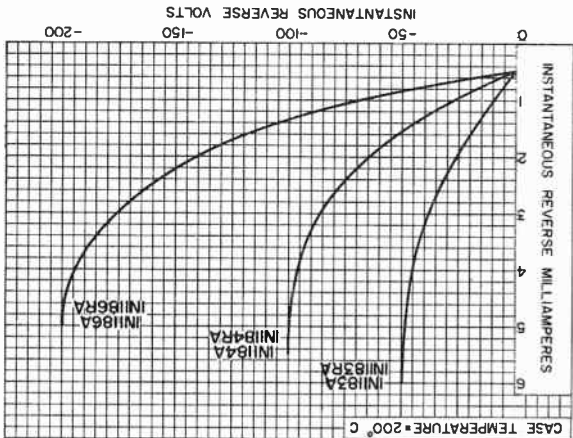


92CS-11350



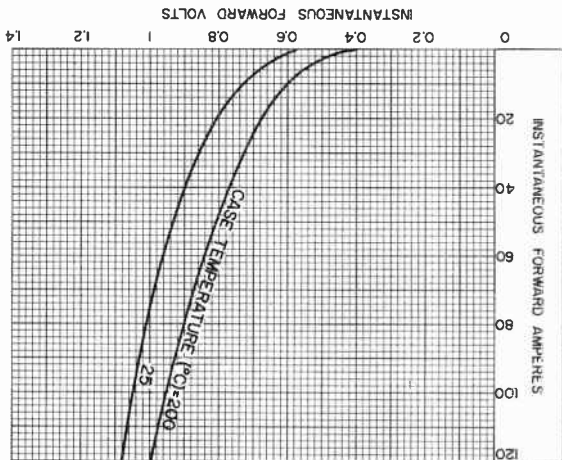


92CS-11335



TYPICAL REVERSE CHARACTERISTICS

92CS-11340



TYPICAL FORWARD CHARACTERISTICS

IN183A, IN183RA



# 1N1184A, 1N1184RA

## Silicon Rectifiers

### DIFFUSED-JUNCTION TYPES

For Industrial and Military Power Supplies

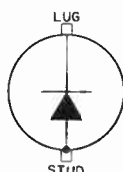
#### GENERAL DATA

##### Mechanical:

Operating Position. . . . . Any  
Dimensions. . . . . See *Dimensional Outline*  
Dimensional Outline . . . . . JEDEC No. DO-5  
Case. . . . . Metal  
Seals . . . . . Hermetic  
Terminal Diagrams (See *Dimensional Outline*):

Type 1N1184A

Type 1N1184RA



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

#### HALF-WAVE RECTIFIER

Maximum and Minimum Ratings, *Absolute-Maximum Values*:

*For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load*

PEAK REVERSE VOLTAGE. . . . . 100 max. volts  
RMS SUPPLY VOLTAGE. . . . . 70 max. volts  
DC BLOCKING VOLTAGE . . . . . 100 max. volts

##### AVERAGE FORWARD CURRENT:

At case temperature of 150° C . . . . . 40 max. amp  
At other case temperatures. . . See *Average-Forward-Current Rating Chart*

PEAK RECURRENT CURRENT. . . . . 195 max. amp

##### PEAK SURGE CURRENT:<sup>a</sup>

For one-half cycle, sine wave . . . . . 800 max. amp  
For one or more cycles. . . . . See *Peak-Surge-Current Rating Chart*

##### CASE-TEMPERATURE RANGE:

Operating and storage . . . . . -65 to +200 °C

##### Characteristics:

Maximum Forward Voltage Drop<sup>b</sup> . . . . . 0.65 volt

##### Maximum Reverse Current:

Dynamic (Averaged over one complete cycle for maximum peak-reverse volts = 100, dc forward amperes = 40, case temperature (°C) = 150) . . . . . 2.5 ma



# 1N1184A, 1N1184RA

Static (DC value for maximum peak-reverse  
volts = 100, case temperature ( $^{\circ}\text{C}$ ) = 25). 0.025 ma

Maximum Thermal Resistance:

Junction-to-case . . . . . 1  $^{\circ}\text{C}/\text{watt}$

<sup>a</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>b</sup> Average value for one complete cycle, for maximum peak reverse volts = 100, dc forward amperes = 40, case temperature ( $^{\circ}\text{C}$ ) = 150.

OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHARTS,  
and  
CURVES

shown under Types 1N1183A and 1N1183RA also apply to the  
1N1184A and 1N1184RA





# 1N1186A, 1N1186RA

## Silicon Rectifiers

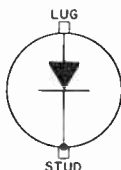
DIFFUSED-JUNCTION TYPES  
For Industrial and Military Power Supplies

### GENERAL DATA

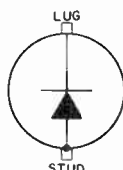
#### Mechanical:

Operating Position. . . . . Any  
Dimensions. . . . . See *Dimensional Outline*  
Dimensional Outline. . . . . JEDEC No. D0-5  
Case. . . . . Metal  
Seals. . . . . Hermetic  
Terminal Diagrams (See *Dimensional Outline*):

Type 1N1186A



Type 1N1186RA



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load

PEAK REVERSE VOLTAGE. . . . . 200 max. volts  
RMS SUPPLY VOLTAGE. . . . . 140 max. volts  
DC BLOCKING VOLTAGE. . . . . 200 max. volts

#### AVERAGE FORWARD CURRENT:

At case temperature of 150° C . . . . . 40 max. amp  
At other case temperatures. . . See *Average-Forward-Current Rating Chart*

PEAK RECURRENT CURRENT. . . . . 195 max. amp

#### PEAK SURGE CURRENT:<sup>a</sup>

For one-half cycle, sine wave . . . . . 800 max. amp  
For one or more cycles. . . See *Peak-Surge-Current Rating Chart*

#### CASE-TEMPERATURE RANGE:

Operating and storage . . . . . -65 to +200 °C

#### Characteristics:

Maximum Forward Voltage Drop<sup>b</sup> . . . . . 0.65 volt

#### Maximum Reverse Current:

Dynamic (Averaged over one complete cycle for maximum peak-reverse volts = 200, dc forward amperes = 40, case temperature (°C) = 150). . . . . 2.5 ma



# 1N1186A, 1N1186RA

Static (DC value for maximum peak-  
reverse volts = 200, case tempera-  
ture ( $^{\circ}\text{C}$ ) = 25) . . . . . 0.025 ma

Maximum Thermal Resistance:

Junction-to-case. . . . . 1  $^{\circ}\text{C}/\text{watt}$

<sup>a</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>b</sup> Average value for one complete cycle, for maximum peak-reverse volts = 200, dc forward amperes = 40, case temperature ( $^{\circ}\text{C}$ ) = 150.

**OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHARTS,  
and  
CURVES**

shown under Types 1N1183A and 1N1183RA also apply to the  
1N1186A and 1N1186RA



# 1N1187, 1N1187R

## Silicon Rectifiers

### DIFFUSED-JUNCTION TYPES

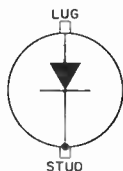
For Industrial and Military Power Supplies

### GENERAL DATA

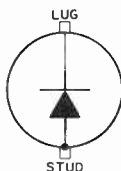
#### Mechanical:

Operating Position. . . . . Any  
 Dimensions. . . . . See *Dimensional Outline*  
 Dimensional Outline. . . . . JEDEC No. DO-5  
 Case. . . . . Metal  
 Seals. . . . . Hermetic  
 Terminal Diagrams (See *Dimensional Outline*):

Type 1N1187



Type 1N1187R



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load

PEAK REVERSE VOLTAGE. . . . . 300 max. volts  
 RMS SUPPLY VOLTAGE. . . . . 212 max. volts  
 DC BLOCKING VOLTAGE. . . . . 240 max. volts

#### AVERAGE FORWARD CURRENT:

At case temperature of 140° C . . . . . 35 max. amp  
 At other case temperatures. . . See *Average-Forward-Current Rating Chart*

PEAK RECURRENT CURRENT. . . . . 130 max. amp

#### PEAK SURGE CURRENT:<sup>a</sup>

For one-half cycle, sine wave . . . . . 500 max. amp  
 For one or more cycles. . . . . See *Peak-Surge-Current Rating Chart*

#### CASE-TEMPERATURE RANGE:

Operating and storage . . . . . -65 to +175 °C

#### Characteristics:

Maximum Forward Voltage Drop<sup>b</sup> . . . . . 1.7 volts

#### Maximum Reverse Current:

Dynamic (Averaged over one complete cycle for maximum peak-reverse volts = 300, dc forward amperes = 35, case temperature (°C) = 140) . . . . . 10 ma



# 1N1187, 1N1187R

Static (DC value for maximum peak-reverse volts = 300, case temperature ( $^{\circ}\text{C}$ ) = 25). . . . .	0.025	ma
Maximum Thermal Resistance: Junction-to-case. . . . .	1	$^{\circ}\text{C}/\text{watt}$

- <sup>a</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.
- <sup>b</sup> Peak value for maximum average forward amperes = 35, case temperature ( $^{\circ}\text{C}$ ) = 140.

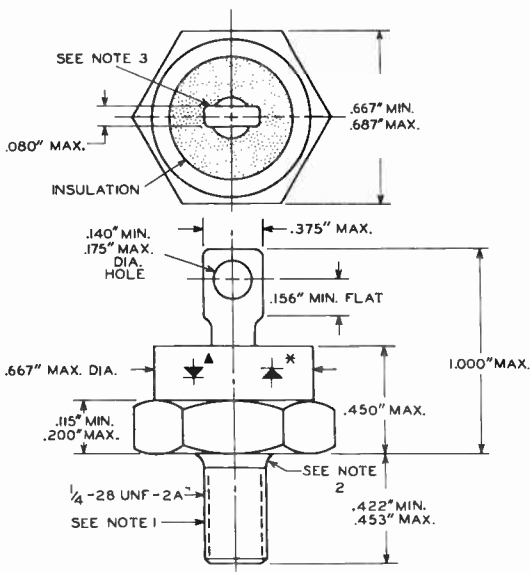
## OPERATING CONSIDERATIONS

Because these rectifiers may operate at voltages which are dangerous, care should be taken in the design of equipment to prevent the operator from coming in contact with the rectifier.

The recommended installation torque is 26 to 36 inch-pounds applied to a 1/4-28 UNF-2B hex nut assembled on stud thread.

The applied torque during installation should not exceed 50 inch-pounds.

JEDEC No. D0-5



92C5-10758R3



# 1N1187, 1N1187R

NOTE 1: MUST WITHSTAND TORQUE OF 30 INCH-POUNDS APPLIED TO 1/4-28 UNF-28 NUT ASSEMBLED ON STUD THREAD.

NOTE 2: DIAMETER OF UNTHREADED PORTION: 0.249" MAXIMUM, 0.220" MINIMUM.

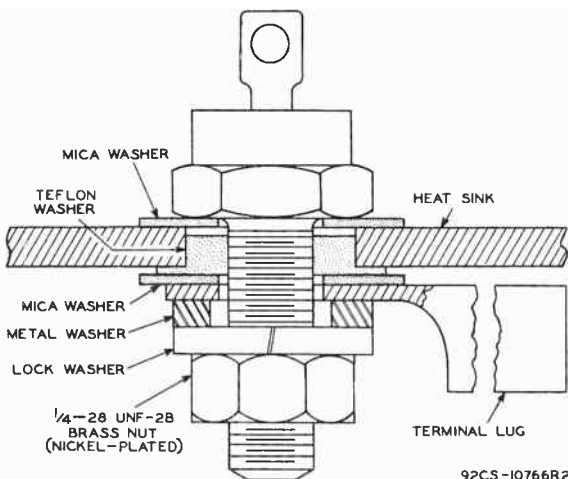
NOTE 3: ANGULAR ORIENTATION OF THIS TERMINAL UNDEFINED.

▲ Polarity symbol for types 1N1187, 1N1188, 1N1189, and 1N1190.

\* Polarity symbol for types 1N1187R, 1N1188R, 1N1189R, and 1N1190R.

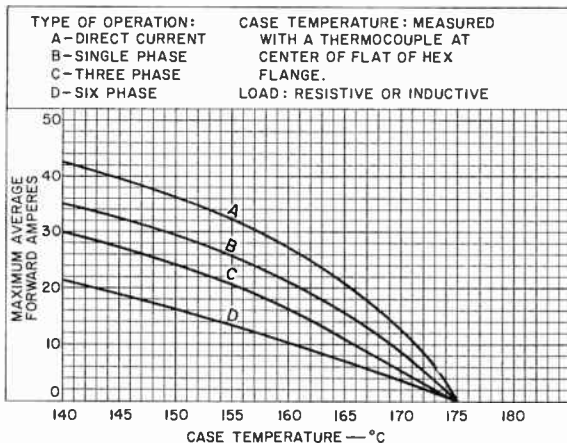
## SUGGESTED MOUNTING ARRANGEMENT

*Mounting components of the type shown are furnished with each silicon rectifier. The increase in thermal resistance with these mounting components is approximately 1.5 °C/watt.*



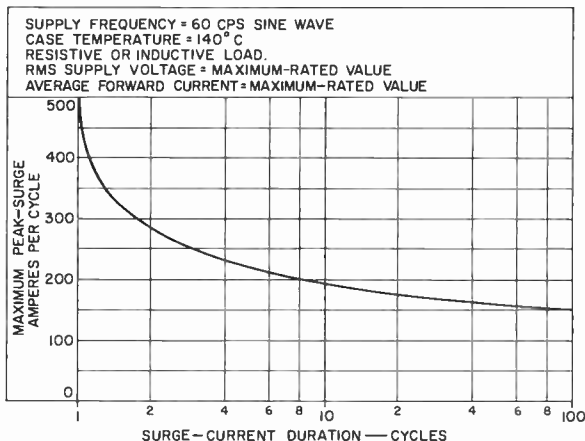
# 1N1187, 1N1187R

## AVERAGE-FORWARD-CURRENT RATING CHART



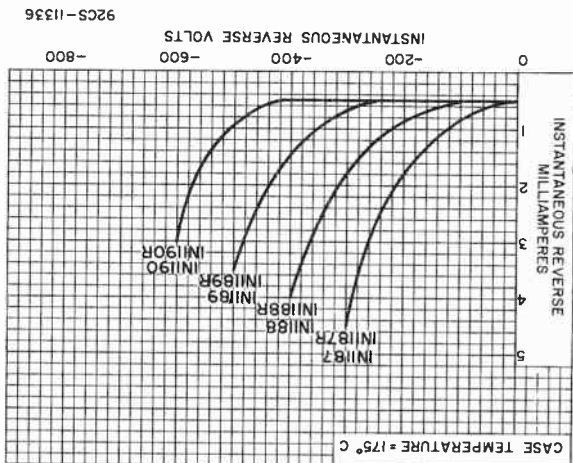
92CS-11342

## PEAK-SURGE-CURRENT RATING CHART

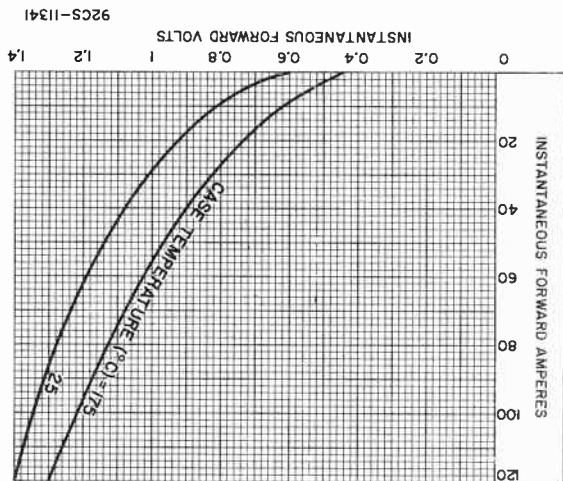


92CS-11351





TYPICAL REVERSE CHARACTERISTICS



TYPICAL FORWARD CHARACTERISTICS

# IN187, IN187R





# 1N1188, 1N1188R

## Silicon Rectifiers

### DIFFUSED-JUNCTION TYPES

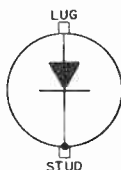
For Industrial and Military Power Supplies

### GENERAL DATA

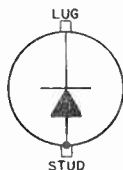
#### Mechanical:

Operating Position. . . . . Any  
 Dimensions. . . . . See *Dimensional Outline*  
 Dimensional Outline. . . . . JFDEC No. DO-5  
 Case. . . . . Metal  
 Seals. . . . . Hermetic  
 Terminal Diagrams (See *Dimensional Outline*):

Type 1N1188



Type 1N1188R



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load

PEAK REVERSE VOLTAGE. . . . . 400 max. volts  
 RMS SUPPLY VOLTAGE. . . . . 284 max. volts  
 DC BLOCKING VOLTAGE. . . . . 320 max. volts

#### AVERAGE FORWARD CURRENT:

At case temperature of 140° C. . . . . 35 max. amp  
 At other case temperatures. . . See *Average-Forward-Current Rating Chart*

PEAK RECURRENT CURRENT. . . . . 130 max. amp

#### PEAK SURGE CURRENT:<sup>a</sup>

For one-half cycle, sine wave. . . . . 500 max. amp  
 For one or more cycles. . . . . See *Peak-Surge-Current Rating Chart*

#### CASE-TEMPERATURE RANGE:

Operating and storage. . . . . -65 to +175 °C

#### Characteristics:

Maximum Forward Voltage Drop<sup>b</sup>. . . . . 1.7 volts

#### Maximum Reverse Current:

Dynamic (Averaged over one complete cycle for maximum peak-reverse volts = 400, dc forward amperes = 35, case temperature (°C) = 140. . . . . 10 ma



# 1N1188, 1N1188R

Static (DC value for maximum peak-reverse  
volts = 400, case temperature ( $^{\circ}\text{C}$ ) = 25). 0.025 ma

Maximum Thermal Resistance:

Junction-to-case. . . . . 1  $^{\circ}\text{C}/\text{watt}$

<sup>a</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>b</sup> Peak value for maximum average forward amperes = 35, case temperature ( $^{\circ}\text{C}$ ) = 140.

OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHARTS,  
and  
CURVES

shown under Types 1N1187 and 1N1187R also apply to the  
1N1188 and 1N1188R



# 1N1189, 1N1189R

## Silicon Rectifiers

DIFFUSED-JUNCTION TYPES  
For Industrial and Military Power Supplies

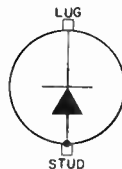
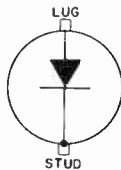
### GENERAL DATA

#### Mechanical:

Operating Position. . . . . Any  
 Dimensions. . . . . See *Dimensional Outline*  
 Dimensional Outline . . . . . JEDEC No. D0-5  
 Case. . . . . Metal  
 Seals . . . . . Hermetic  
 Terminal Diagrams (See *Dimensional Outline*):

Type 1N1189

Type 1N1189R



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load

PEAK REVERSE VOLTAGE. . . . . 500 max. volts  
 RMS SUPPLY VOLTAGE. . . . . 355 max. volts  
 DC BLOCKING VOLTAGE . . . . . 400 max. volts

#### AVERAGE FORWARD CURRENT:

At case temperature of 140° C . . . . . 35 max. amp  
 At other case temperatures. . . See *Average-Forward-Current Rating Chart*

PEAK RECURRENT CURRENT. . . . . 130 max. amp

#### PEAK SURGE CURRENT:<sup>a</sup>

For one-half cycle, sine wave . . . . . 500 max. amp  
 For one or more cycles. . . . . See *Peak-Surge-Current Rating Chart*

#### CASE-TEMPERATURE RANGE:

Operating and storage . . . . . -65 to +175 °C

#### Characteristics:

Maximum Forward Voltage Drop<sup>b</sup> . . . . . 1.7 volts

#### Maximum Reverse Current:

Dynamic (Averaged over one complete cycle for maximum peak-reverse volts = 500, dc forward amperes = 35, case temperature (°C) = 140). . . . . 10 ma



# 1N1189, 1N1189R

Static (DC value for maximum peak-reverse volts = 500, case temperature ( $^{\circ}\text{C}$ ) = 25) . . . . .	0.025	ma
Maximum Thermal Resistance: Junction-to-case. . . . .	1	$^{\circ}\text{C}/\text{watt}$

- a Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.
- b Peak value for maximum average forward amperes = 35, case temperature ( $^{\circ}\text{C}$ ) = 140.

OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHARTS,  
and  
CURVES

shown under Types 1N1187 and 1N1187R also apply to the  
1N1189 and 1N1189R



# 1N1190, 1N1190R

## Silicon Rectifiers

### DIFFUSED-JUNCTION TYPES

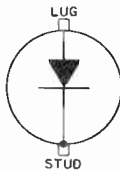
For Industrial and Military Power Supplies

#### GENERAL DATA

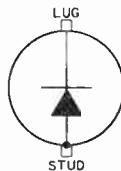
##### Mechanical:

Operating Position. . . . . Any  
Dimensions. . . . . See *Dimensional Outline*  
Dimensional Outline. . . . . JEDEC No. D0-5  
Case. . . . . Metal  
Seals. . . . . Hermetic  
Terminal Diagrams (See *Dimensional Outline*):

Type 1N1190



Type 1N1190R



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

#### HALF-WAVE RECTIFIER

##### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load

PEAK REVERSE VOLTAGE. . . . . 600 max. volts  
RMS SUPPLY VOLTAGE. . . . . 424 max. volts  
DC BLOCKING VOLTAGE. . . . . 480 max. volts

##### AVERAGE FORWARD CURRENT:

At case temperature of 140° C . . . . . 35 max. amp  
At other case temperatures. . . See *Average-Forward-Current Rating Chart*

PEAK RECURRENT CURRENT. . . . . 130 max. amp

##### PEAK SURGE CURRENT:<sup>a</sup>

For one-half cycle, sine wave . . . . . 500 max. amp  
For one or more cycles. . . . . See *Peak-Surge-Current Rating Chart*

##### CASE-TEMPERATURE RANGE:

Operating and storage . . . . . -65 to +175 °C

##### Characteristics:

Maximum Forward Voltage Drop<sup>b</sup> . . . . . 1.7 volts

##### Maximum Reverse Current:

Dynamic (Averaged over one complete cycle for maximum peak-reverse volts = 600, dc forward amperes = 35, case temperature (°C) = 140). . . . . 10 ma



# 1N1190, 1N1190R

Static (DC value for maximum peak-reverse  
volts = 600, case temperature ( $^{\circ}\text{C}$ )  
= 25) . . . . . 0.025 ma

Maximum Thermal Resistance:

Junction-to-case. . . . . 1  $^{\circ}\text{C}/\text{watt}$

- <sup>a</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.
- <sup>b</sup> Peak value for maximum average forward amperes = 35, case temperature ( $^{\circ}\text{C}$ ) = 140.

OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHARTS,  
and  
CURVES

shown under Types 1N1187 and 1N1187R also apply to the  
1N1190 and 1N1190R



# 1N1195A, 1N1195RA

## Silicon Rectifiers

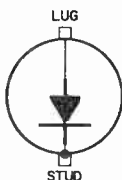
DIFFUSED-JUNCTION TYPES  
For Industrial and Military Power Supplies

### GENERAL DATA

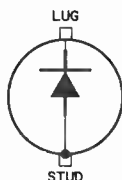
#### Mechanical:

Operating Position. . . . . Any  
Dimensions. . . . . See *Dimensional Outline*  
Dimensional Outline . . . . . JEDEC No. DO-5  
Case. . . . . Metal  
Seals . . . . . Hermetic  
Terminal Diagrams (See *Dimensional Outline*):

Type 1N1195A



Type 1N1195RA



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load

PEAK INVERSE VOLTAGE. . . . . 300 max. volts  
RMS SUPPLY VOLTAGE. . . . . 212 max. volts  
DC BLOCKING VOLTAGE . . . . . 300 max. volts

#### AVERAGE FORWARD CURRENT:

At case temperature of 150° C . . . . . 20 max. amp  
At other case temperatures. . . See *Average-Forward-Current*

*Rating Chart*

PEAK RECURRENT CURRENT. . . . . 90 max. amp

#### PEAK SURGE CURRENT:<sup>a</sup>

For one-half cycle, sine wave . . . . . 350 max. amp

For one or more cycles. . . . . See *Peak-Surge-Current*  
*Rating Chart*

#### CASE-TEMPERATURE RANGE:

Operating and storage . . . . . -65 to +175 °C

#### Characteristics:

At case temperature of 150° C and maximum-rated voltage and average forward current

Maximum Forward Voltage Drop. . . . . 0.6 volt

Maximum Reverse Current . . . . . 3.2 ma



# 1N1195A, 1N1195RA

<sup>a</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHARTS,  
and  
CURVES

shown under Type 1N248C and 1N248RC also apply to the  
1N1195A and 1N1195RA





# 1N1196A, 1N1196RA

## Silicon Rectifiers

### DIFFUSED-JUNCTION TYPES

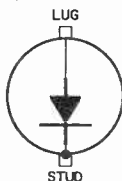
For Industrial and Military Power Supplies

#### GENERAL DATA

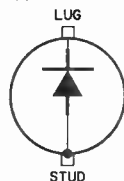
##### Mechanical:

Operating Position. . . . . Any  
Dimensions. . . . . See *Dimensional Outline*  
Dimensional Outline. . . . . JEDEC No. D0-5  
Case. . . . . Metal  
Seals. . . . . Hermetic  
Terminal Diagrams (See *Dimensional Outline*):

Type 1N1196A



Type 1N1196RA



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

#### HALF-WAVE RECTIFIER

##### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load

PEAK INVERSE VOLTAGE. . . . . 400 max. volts  
RMS SUPPLY VOLTAGE. . . . . 284 max. volts  
DC BLOCKING VOLTAGE. . . . . 400 max. volts

##### AVERAGE FORWARD CURRENT:

At case temperature of 150° C . . . . . 20 max. amp  
At other case temperatures. . . See *Average-Forward-Current Rating Chart*

PEAK RECURRENT CURRENT. . . . . 90 max. amp

##### PEAK SURGE CURRENT:<sup>a</sup>

For one-half cycle, sine wave . . . . . 350 max. amp  
For one or more cycles. . . . . See *Peak-Surge-Current Rating Chart*

##### CASE-TEMPERATURE RANGE:

Operating and storage . . . . . -65 to +175 °C

##### Characteristics:

At case temperature of 150° C and maximum-rated voltage and average forward current

Maximum Forward Voltage Drop. . . . . 0.6 volt  
Maximum Reverse Current . . . . . 2.5 ma



# 1N1196A, 1N1196RA

<sup>a</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHARTS,  
and  
CURVES

shown under Types 1N248C and 1N248RC also apply to the  
1N1196A and 1N1196RA



# 1N1197A, 1N1197RA

## Silicon Rectifiers

### DIFFUSED-JUNCTION TYPES

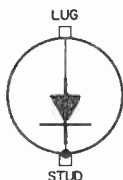
For Industrial and Military Power Supplies

#### GENERAL DATA

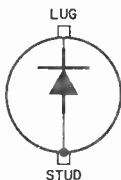
##### Mechanical:

Operating Position. . . . . Any  
Dimensions. . . . . See *Dimensional Outline*  
Dimensional Outline . . . . . JEDEC No. D0-5  
Case. . . . . Metal  
Seals . . . . . Hermetic  
Terminal Diagrams (See *Dimensional Outline*):

Type 1N1197A



Type 1N1197RA



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

#### HALF-WAVE RECTIFIER

##### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load

PEAK INVERSE VOLTAGE. . . . .	500 max.	volts
RMS SUPPLY VOLTAGE. . . . .	355 max.	volts
DC BLOCKING VOLTAGE . . . . .	500 max.	volts
AVERAGE FORWARD CURRENT:		
At case temperature of 150° C . . . . .	20 max.	amp
At other case temperatures. . . See <i>Average-Forward-Current Rating Chart</i>		
PEAK RECURRENT CURRENT. . . . .	90 max.	amp
PEAK SURGE CURRENT: <sup>a</sup>		
For one-half cycle, sine wave . . . . .	350 max.	amp
For one or more cycles. . See <i>Peak-Surge-Current Rating Chart</i>		
CASE-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +175	°C

##### Characteristics:

At case temperature of 150° C and maximum-rated voltage and average forward current

Maximum Forward Voltage Drop. . . . .	0.6	volt
Maximum Reverse Current . . . . .	2.2	ma



# 1N1197A, 1N1197RA

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<sup>a</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHARTS,

and  
CURVES

shown under Type 1N248C and 1N248RC also apply to the  
1N1197A and 1N1197RA



# 1N1198A, 1N1198RA

## Silicon Rectifiers

### DIFFUSED-JUNCTION TYPES

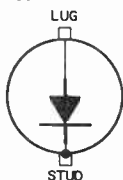
For Industrial and Military Power Supplies

### GENERAL DATA

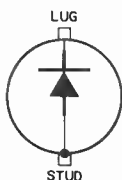
#### Mechanical:

Operating Position. . . . . Any  
Dimensions. . . . . See *Dimensional Outline*  
Dimensional Outline . . . . . JEDEC No. DO-5  
Case. . . . . Metal  
Seals . . . . . Hermetic  
Terminal Diagrams (See *Dimensional Outline*):

Type 1N1198A



Type 1N1198RA



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

Maximum and Minimum Ratings, Absolute-Maximum Values:

*For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load*

PEAK INVERSE VOLTAGE. . . . . 600 max. volts  
RMS SUPPLY VOLTAGE. . . . . 424 max. volts  
DC BLOCKING VOLTAGE . . . . . 600 max. volts

#### AVERAGE FORWARD CURRENT:

At case temperature of 150° C . . . . . 20 max. amp  
At other case temperatures. . . See *Average-Forward-Current*

*Rating Chart*

PEAK RECURRENT CURRENT. . . . . 90 max. amp

#### PEAK SURGE CURRENT:<sup>a</sup>

For one-half cycle, sine wave . . . . . 350 max. amp  
For one or more cycles. . See *Peak-Surge-Current Rating Chart*

#### CASE-TEMPERATURE RANGE:

Operating and storage . . . . . -65 to +175 °C

#### Characteristics:

*At case temperature of 150° C and maximum-rated voltage and average forward current*

Maximum Forward Voltage Drop. . . . . 0.6 volt  
Maximum Reverse Current . . . . . 1.5 ma



# 1N1198A, 1N1198RA

<sup>a</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHARTS,  
and  
CURVES

shown under Types 1N248C and 1N248RC also apply to the  
1N1198A and 1N1198RA



# 1N1199A, 1N1199RA

## Silicon Rectifiers

### DIFFUSED-JUNCTION TYPES

For Industrial and Military Power Supplies

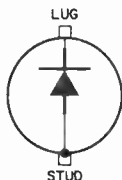
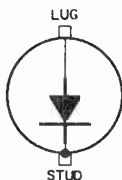
#### GENERAL DATA

##### Mechanical:

Operating Position. . . . . Any  
Dimensions. . . . . See *Dimensional Outline*  
Dimensional Outline. . . . . JEDEC No. D0-4  
Case. . . . . Metal  
Seals. . . . . Hermetic  
Terminal Diagrams (See *Dimensional Outline*):

Type 1N1199A

Type 1N1199RA



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

#### HALF-WAVE RECTIFIER

##### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load

PEAK INVERSE VOLTAGE. . . . .	50 max.	volts
TRANSIENT INVERSE VOLTAGE: Non-repetitive, for duration of 5-milliseconds maximum. . . . .	100 max.	volts
RMS SUPPLY VOLTAGE. . . . .	35 max.	volts
DC BLOCKING VOLTAGE. . . . .	50 max.	volts
AVERAGE FORWARD CURRENT: At case temperature of 150° C . . . . .	12 max.	amp
At other case temperatures. . . . .	See <i>Average-Forward-Current Rating Chart</i>	
PEAK RECURRENT CURRENT. . . . .	50 max.	amp
PEAK SURGE CURRENT: <sup>a</sup> For one-half cycle, sine wave . . . . .	240 max.	amp
For one or more cycles. . . . .	See <i>Peak-Surge-Current Rating Chart</i>	
CASE-TEMPERATURE RANGE: Operating and storage . . . . .	-65 to +200	°C
Characteristics:		
Maximum Forward Voltage Drop <sup>b</sup> . . . . .	0.55	volt
Maximum Reverse Current <sup>b</sup> . . . . .	3	ma



# 1N1199A, 1N1199RA

Maximum Thermal Resistance:

Junction-to-case. . . . . 2 °C/watt

- <sup>a</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.
- <sup>b</sup> At case temperature of 150° C and maximum-rated voltage and average forward current.

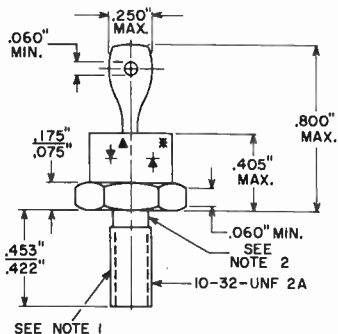
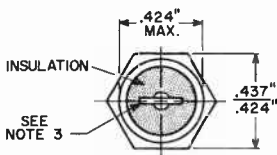
## OPERATING CONSIDERATIONS

Because these rectifiers may operate at voltages which are dangerous, care should be taken in the design of equipment to prevent the operator from coming in contact with the rectifier.

The recommended installation torque is 15 to 20 inch-pounds applied to a 10-32 UNF-2B hex nut assembled on stud thread.

The applied torque during installation should not exceed 25 inch-pounds.

JEDEC No. D0-4



92CS-11070R1





# 1N1199A, 1N1199RA

**NOTE 1:** NORMAL INSTALLATION TORQUE IS 15 TO 20 INCH-POUNDS APPLIED TO A 10-32 UNF-28 HEX NUT ASSEMBLED ON STUD THREADS. UNDER NO CIRCUMSTANCES SHOULD THIS VALUE EXCEED 25 INCH-POUNDS.

**NOTE 2:** DIAMETER OF UNTHREADED PORTION: 0.189" MAXIMUM, 0.169" MINIMUM.

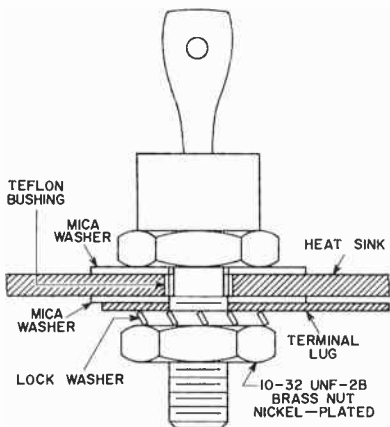
**NOTE 3:** ANGULAR ORIENTATION OF THIS TERMINAL UNDEFINED.

**▲** Polarity symbol for types 1N1199A, 1N1200A, 1N1202A, 1N1203A, 1N1204A, 1N1205A, and 1N1206A.

**\*** Polarity symbol for types 1N1199RA, 1N1206RA, 1N1202RA, 1N1203RA, 1N1204RA, 1N1205RA, and 1N1206RA.

## SUGGESTED MOUNTING ARRANGEMENT

*Mounting components of the type shown are furnished with each silicon rectifier*



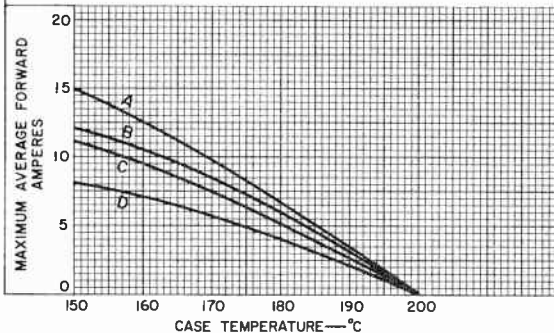
92CS-11072R1



# 1N1199A, 1N1199RA

## AVERAGE-FORWARD-CURRENT RATING CHART

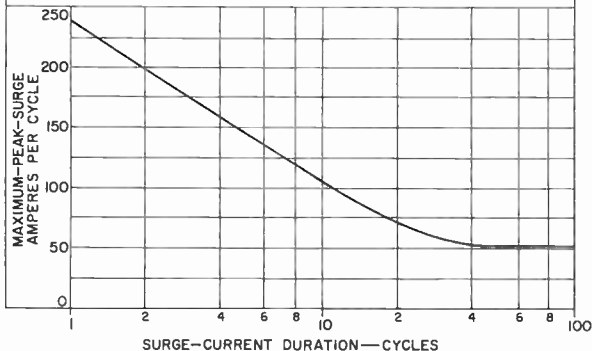
TYPE OF OPERATION: CASE TEMPERATURE: MEASURED WITH A  
A-DIRECT CURRENT THERMOCOUPLE AT  
B-SINGLE PHASE CENTER OF FLAT  
C-THREE PHASE OF HEX FLANGE  
D-SIX PHASE LOAD: RESISTIVE OR  
INDUCTIVE



92CS-11065RI

## PEAK-SURGE-CURRENT RATING CHART

SUPPLY FREQUENCY=60 CPS SINE WAVE  
CASE TEMPERATURE=150° C  
RESISTIVE OR INDUCTIVE LOAD.  
RMS SUPPLY VOLTAGE=MAXIMUM-RATED VALUE  
AVERAGE FORWARD CURRENT=MAXIMUM-RATED VALUE

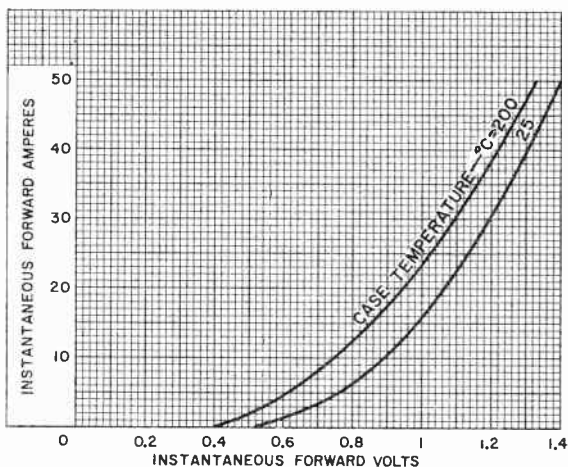


92CS-11066RI



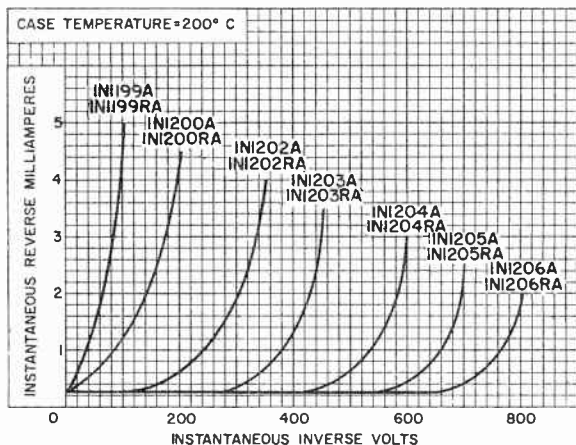
# 1N1199A, 1N1199RA

## TYPICAL FORWARD CHARACTERISTICS



92CS-11063

## TYPICAL REVERSE CHARACTERISTICS



92CS-11064R1





# 1N1200A, 1N1200RA

## Silicon Rectifiers

### DIFFUSED-JUNCTION TYPES

For Industrial and Military Power Supplies

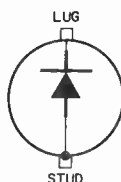
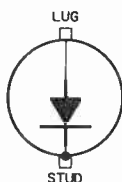
### GENERAL DATA

#### Mechanical:

Operating Position. . . . . Any  
Dimensions. . . . . See *Dimensional Outline*  
Dimensional Outline . . . . . JEDEC No. D0-4  
Case. . . . . Metal  
Seals . . . . . Hermetic  
Terminal Diagrams (See *Dimensional Outline*):

Type 1N1200A

Type 1N1200RA



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

Maximum and Minimum Ratings, Absolute-Maximum Values:

*For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load*

PEAK INVERSE VOLTAGE. . . . .	100 max.	volts
TRANSIENT INVERSE VOLTAGE: Non-repetitive, for duration of 5-milliseconds maximum. . . . .	200 max.	volts
RMS SUPPLY VOLTAGE. . . . .	70 max.	volts
DC BLOCKING VOLTAGE . . . . .	100 max.	volts
AVERAGE FORWARD CURRENT: At case temperature of 150° C . . . . .	12 max.	amp
At other case temperatures. . . . .	See <i>Average-Forward-Current Rating Chart</i>	
PEAK RECURRENT CURRENT. . . . .	50 max.	amp
PEAK SURGE CURRENT: <sup>a</sup> For one-half cycle, sine wave . . . . .	240 max.	amp
For one or more cycles. . . . .	See <i>Peak-Surge-Current Rating Chart</i>	
CASE-TEMPERATURE RANGE: Operating and storage . . . . .	-65 to +200	°C



# 1N1200A, 1N1200RA

## Characteristics:

Maximum Forward Voltage Drop <sup>b</sup> . . . . .	0.55	volt
Maximum Reverse Current <sup>b</sup> . . . . .	2.5	ma
Maximum Thermal Resistance:		
Junction-to-case. . . . .	2	°C/watt

<sup>a</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>b</sup> At case temperature of 150° C and maximum-rated voltage and average forward current.

OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHARTS,  
and  
CURVES

shown under Types 1N1199A and 1N1199RA also apply to the  
1N1200A and 1N1200RA



# 1N1202A, 1N1202RA

## Silicon Rectifiers

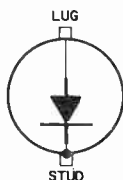
DIFFUSED-JUNCTION TYPES  
For Industrial and Military Power Supplies

### GENERAL DATA

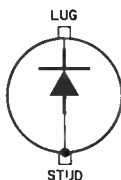
#### Mechanical:

Operating Position. . . . . Any  
Dimensions. . . . . See *Dimensional Outline*  
Dimensional Outline. . . . . JEDEC No. D0-4  
Case. . . . . Metal  
Seals. . . . . Hermetic  
Terminal Diagrams (See *Dimensional Outline*):

Type 1N1202A



Type 1N1202RA



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load

PEAK INVERSE VOLTAGE. . . . .	200 max.	volts
TRANSIENT INVERSE VOLTAGE:		
Non-repetitive, for duration of		
5-milliseconds maximum. . . . .	350 max.	volts
RMS SUPPLY VOLTAGE. . . . .	140 max.	volts
DC BLOCKING VOLTAGE. . . . .	200 max.	volts
AVERAGE FORWARD CURRENT:		
At case temperature of 150° C . . . . .	12 max.	amp
At other case temperatures. . . . .	See <i>Average-Forward-Current Rating Chart</i>	
PEAK RECURRENT CURRENT. . . . .	50 max.	amp
PEAK SURGE CURRENT: <sup>a</sup>		
For one-half cycle, sine wave . . . . .	240 max.	amp
For one or more cycles. . . . .	See <i>Peak-Surge-Current Rating Chart</i>	
CASE-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +200	°C
Characteristics:		
Maximum Forward Voltage Drop <sup>b</sup> . . . . .	0.55	volt
Maximum Reverse Current <sup>b</sup> . . . . .	2	ma



# 1N1202A, 1N1202RA

Maximum Thermal Resistance:

Junction-to-case. . . . . 2 °C/watt

- <sup>a</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.
- <sup>b</sup> At case temperature of 150° C and maximum-rated voltage and average forward current.

**OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHARTS,  
and  
CURVES**

shown under Types 1N1199A and 1N1199RA also apply to the  
1N1202A and 1N1202RA





# 1N1203A, 1N1203RA

## Silicon Rectifiers

### DIFFUSED-JUNCTION TYPES

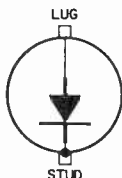
For Industrial and Military Power Supplies

### GENERAL DATA

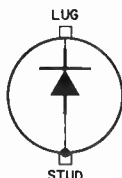
#### Mechanical:

Operating Position. . . . . Any  
Dimensions. . . . . See *Dimensional Outline*  
Dimensional Outline . . . . . JEDEC No. D0-4  
Case. . . . . Metal  
Seals . . . . . Hermetic  
Terminal Diagrams (See *Dimensional Outline*):

Type 1N1203A



Type 1N1203RA



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load

PEAK INVERSE VOLTAGE. . . . .	300 max.	volts
TRANSIENT INVERSE VOLTAGE: Non-repetitive, for duration of 5-milliseconds maximum. . . . .	450 max.	volts
RMS SUPPLY VOLTAGE. . . . .	212 max.	volts
DC BLOCKING VOLTAGE . . . . .	300 max.	volts
AVERAGE FORWARD CURRENT: At case temperature of 150° C . . . . .	12 max.	amp
At other case temperatures. . . . .	See <i>Average-Forward-Current Rating Chart</i>	
PEAK RECURRENT CURRENT. . . . .	50 max.	amp
PEAK SURGE CURRENT: <sup>a</sup> For one-half cycle, sine wave . . . . .	240 max.	amp
For one or more cycles. . . . .	See <i>Peak-Surge-Current Rating Chart</i>	
CASE-TEMPERATURE RANGE: Operating and storage . . . . .	-65 to +200	°C

#### Characteristics:

Maximum Forward Voltage Drop <sup>b</sup> . . . . .	0.55	volt
Maximum Reverse Current <sup>b</sup> . . . . .	1.75	ma



# 1N1203A, 1N1203RA

Maximum Thermal Resistance:

Junction-to-case. . . . . 2 °C/watt

- <sup>a</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.
- <sup>b</sup> At case temperature of 150° C and maximum-rated voltage and average forward current.

OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHARTS,  
and  
CURVES

shown under Types 1N1199A and 1N1199RA also apply to the  
1N1203A and 1N1203RA



# 1N1204A, 1N1204RA

## Silicon Rectifiers

### DIFFUSED-JUNCTION TYPES

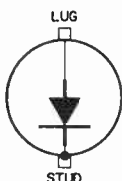
For Industrial and Military Power Supplies

### GENERAL DATA

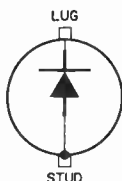
#### Mechanical:

Operating Position. . . . . Any  
Dimensions. . . . . See *Dimensional Outline*  
Dimensional Outline. . . . . JEDEC No. 00-4  
Case. . . . . Metal  
Seals. . . . . Hermetic  
Terminal Diagrams (See *Dimensional Outline*):

Type 1N1204A



Type 1N1204RA



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load

PEAK INVERSE VOLTAGE. . . . .	400 max.	volts
TRANSIENT INVERSE VOLTAGE: Non-repetitive, for duration of 5-milliseconds maximum. . . . .	600 max.	volts
RMS SUPPLY VOLTAGE. . . . .	284 max.	volts
DC BLOCKING VOLTAGE. . . . .	400 max.	volts
AVERAGE FORWARD CURRENT: At case temperature of 150° C . . . . .	12 max.	amp
At other case temperatures. . . . .	See <i>Average-Forward-Current Rating Chart</i>	
PEAK RECURRENT CURRENT. . . . .	50 max.	amp
PEAK SURGE CURRENT: <sup>a</sup> For one-half cycle, sine wave . . . . .	240 max.	amp
For one or more cycles. . . . .	See <i>Peak-Surge-Current Rating Chart</i>	
CASE-TEMPERATURE RANGE: Operating and storage . . . . .	-65 to +200	°C
<b>Characteristics:</b> Maximum Forward Voltage Drop <sup>b</sup> . . . . .	0.55	volt
Maximum Reverse Current <sup>b</sup> . . . . .	1.5	ma



# 1N1204A, 1N1204RA

Maximum Thermal Resistance:

Junction-to-case. . . . . 2 °C/watt

<sup>a</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>b</sup> At case temperature of 150° C and maximum-rated voltage and average forward current.

**OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHARTS,  
and  
CURVES**

shown under Types 1N1199A and 1N1199RA also apply to the  
1N1204A and 1N1204RA



# 1N1205A, 1N1205RA

## Silicon Rectifiers

### DIFFUSED-JUNCTION TYPES

For Industrial and Military Power Supplies

### GENERAL DATA

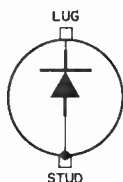
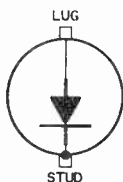
#### Mechanical:

Operating Position. . . . . Any  
Dimensions. . . . . See *Dimensional Outline*  
Dimensional Outline . . . . . JEDEC No. D0-4  
Case. . . . . Metal  
Seals . . . . . Hermetic

Terminal Diagrams (See *Dimensional Outline*):

Type 1N1205A

Type 1N1205RA



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

Maximum and Minimum Ratings, *Absolute-Maximum Values*:

*For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load*

PEAK INVERSE VOLTAGE. . . . .	500 max.	volts
TRANSIENT INVERSE VOLTAGE:		
Non-repetitive, for duration of		
5-milliseconds maximum. . . . .	700 max.	volts
RMS SUPPLY VOLTAGE. . . . .	355 max.	volts
DC BLOCKING VOLTAGE . . . . .	500 max.	volts
AVERAGE FORWARD CURRENT:		
At case temperature of 150° C . . . . .	12 max.	amp
At other case temperatures. . . . .	See <i>Average-Forward-Current Rating Chart</i>	
PEAK RECURRENT CURRENT. . . . .	50 max.	amp
PEAK SURGE CURRENT: <sup>a</sup>		
For one-half cycle, sine wave . . . . .	240 max.	amp
For one or more cycles. . . . .	See <i>Peak-Surge-Current Rating Chart</i>	
CASE-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +200	°C



# 1N1205A, 1N1205RA

## Characteristics:

Maximum Forward Voltage Drop <sup>b</sup> . . . . .	0.55	volt
Maximum Reverse Current <sup>b</sup> . . . . .	1.25	ma
Maximum Thermal Resistance: Junction-to-case. . . . .	2	°C/watt

<sup>a</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>b</sup> At case temperature of 150° C and maximum-rated voltage and average forward current.

OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHARTS,  
and  
CURVES

shown under Types 1N1199A and 1N1199RA also apply to the  
1N1205A and 1N1205RA



# 1N1206A, 1N1206RA

## Silicon Rectifiers

### DIFFUSED-JUNCTION TYPES

For Industrial and Military Power Supplies

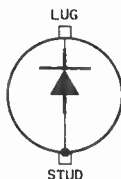
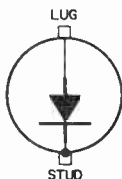
### GENERAL DATA

#### Mechanical:

Operating Position. . . . . Any  
Dimensions. . . . . See *Dimensional Outline*  
Dimensional Outline. . . . . JEDEC No. DO-4  
Case. . . . . Metal  
Seals. . . . . Hermetic  
Terminal Diagrams (See *Dimensional Outline*):

Type 1N1206A

Type 1N1206RA



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load

PEAK INVERSE VOLTAGE. . . . .	600 max.	volts
TRANSIENT INVERSE VOLTAGE:		
Non-repetitive, for duration of 5-milliseconds maximum. . . . .	800 max.	volts
RMS SUPPLY VOLTAGE. . . . .	424 max.	volts
DC BLOCKING VOLTAGE. . . . .	600 max.	volts
AVERAGE FORWARD CURRENT:		
At case temperature of 150° C . . . . .	12 max.	amp
At other case temperatures . . . . .	See <i>Average-Forward-Current Rating Chart</i>	
PEAK RECURRENT CURRENT. . . . .	50 max.	amp
PEAK SURGE CURRENT: <sup>a</sup>		
For one-half cycle, sine wave . . . . .	240 max.	amp
For one or more cycles. . . . .	See <i>Peak-Surge-Current Rating Chart</i>	
CASE-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +200	°C
Characteristics:		
Maximum Forward Voltage Drop <sup>b</sup> . . . . .	0.55	volt
Maximum Reverse Current <sup>b</sup> . . . . .	1	ma



# 1N1206A, 1N1206RA

Maximum Thermal Resistance:

Junction-to-case. . . . . 2 °C/watt

- a Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.
- b At case temperature of 150° C and maximum-rated voltage and average forward current.

**OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHARTS,**

**and  
CURVES**

shown under Types 1N1199A and 1N1199RA also apply to the  
1N1206A and 1N1206RA





# 1N1612, 1N1612R

## Silicon Rectifiers

### DIFFUSED-JUNCTION TYPES

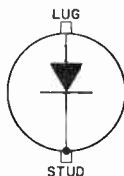
For Industrial and Military Power Supplies

### GENERAL DATA

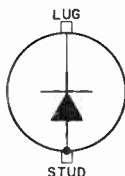
#### Mechanical:

Operating Position. . . . . Any  
 Dimensions. . . . . See *Dimensional Outline*  
 Dimensional Outline. . . . . JEDEC No. DO-4  
 Case. . . . . Metal  
 Seals. . . . . Hermetic  
 Terminal Diagrams (See *Dimensional Outline*):

Type 1N1612



Type 1N1612R



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load

PEAK INVERSE VOLTAGE. . . . .	50 max.	volts
RMS SUPPLY VOLTAGE. . . . .	35 max.	volts
DC BLOCKING VOLTAGE. . . . .	50 max.	volts
AVERAGE FORWARD CURRENT:		
At case temperature of 135° C . . . . .	5 max.	amp
At other case temperatures. . . . .	See <i>Average-Forward-Current Rating Chart</i>	
PEAK RECURRENT CURRENT. . . . .	15 max.	amp
CASE-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +175	°C

#### Characteristics:

Maximum Forward Voltage Drop for dc forward amperes = 10, case temperature (°C) = 25 . . . . .	1.5	volts
Maximum Reverse Current:		
Dynamic (Averaged over one complete cycle for maximum peak-reverse volts = 50, dc forward amperes = 5, case temperature (°C) = 150). . . . .	1	ma
Static (DC value for maximum peak-reverse volts = 50, case temperature (°C) = 25) . . . . .	0.01	ma



# 1N1612, 1N1612R

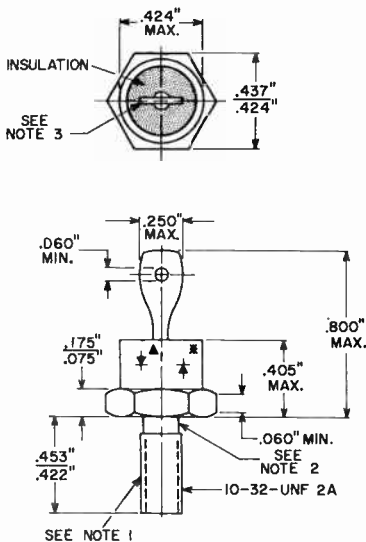
## OPERATING CONSIDERATIONS

Because these rectifiers may operate at voltages which are dangerous, care should be taken in the design of equipment to prevent the operator from coming in contact with the rectifier.

The recommended installation torque is 15 to 20 inch-pounds applied to a 10-32 UNF-2B hex nut assembled on stud thread.

The applied torque during installation should not exceed 25 inch-pounds.

JEDEC No. D0-4



92CS-11070R1

NOTE 1: NORMAL INSTALLATION TORQUE IS 15 TO 20 INCH-POUNDS APPLIED TO A 10-32 UNF-2B HEX NUT ASSEMBLED ON STUD THREADS. UNDER NO CIRCUMSTANCES SHOULD THIS VALUE EXCEED 25 INCH-POUNDS.

NOTE 2: DIAMETER OF UNTHREADED PORTION: D.189" MAXIMUM, D.163" MINIMUM.

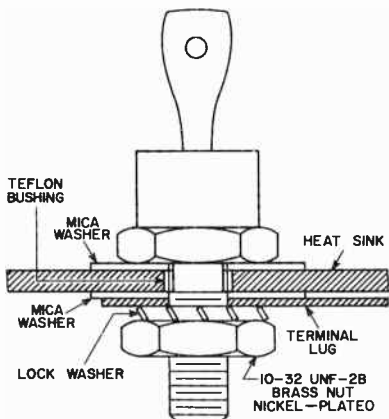
NOTE 3: ANGULAR ORIENTATION OF THIS TERMINAL UNDEFINED.

▲ Polarity symbol for types 1N1612, 1N1613, 1N1614, 1N1615, and 1N1616.

\* Polarity symbol for types 1N1612R, 1N1613R, 1N1614R, 1N1615R, and 1N1616R.

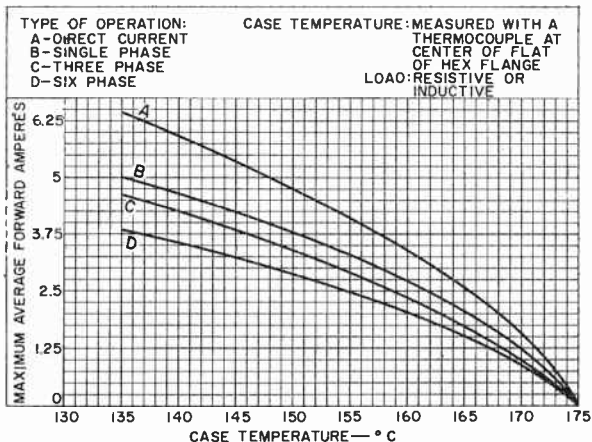
# 1N1612, 1N1612R

## SUGGESTED MOUNTING ARRANGEMENT



92CS-11072R1

## AVERAGE-FORWARD-CURRENT RATING CHART

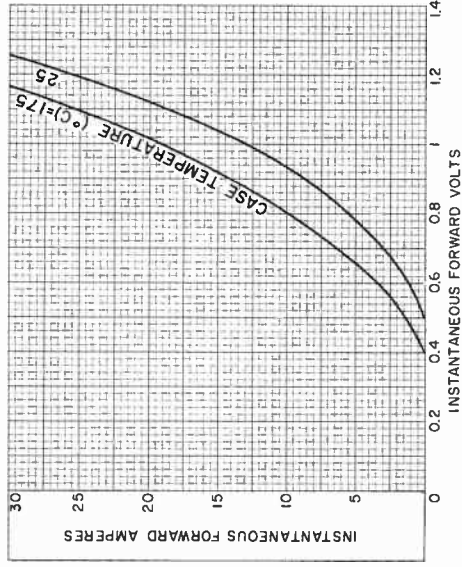


92CS-11295



# 1N1612, 1N1612R

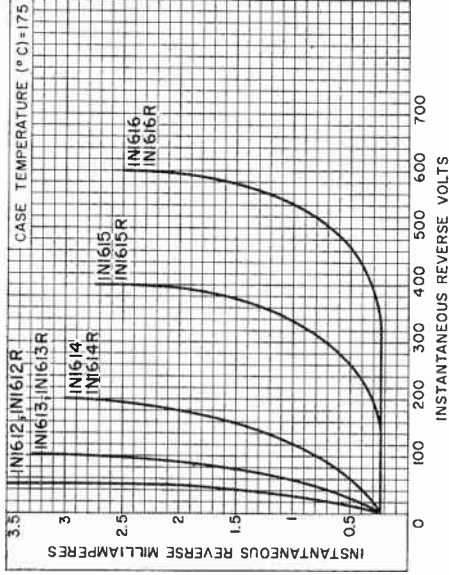
## TYPICAL FORWARD CHARACTERISTICS



World Precision Instrument

92CS-11296

## TYPICAL REVERSE CHARACTERISTICS



92CS-11297

# 1N1613, 1N1613R

## Silicon Rectifiers

### DIFFUSED-JUNCTION TYPES

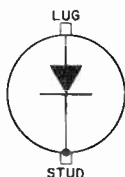
For Industrial and Military Power Supplies

### GENERAL DATA

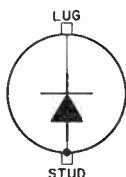
#### Mechanical:

Operating Position. . . . . Any  
 Dimensions. . . . . See *Dimensional Outline*  
 Dimensional Outline. . . . . JEDEC No. D0-4  
 Case. . . . . Metal  
 Seals. . . . . Hermetic  
 Terminal Diagrams (See *Dimensional Outline*):

Type 1N1613



Type 1N1613R



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

Maximum and Minimum Ratings, *Absolute-Maximum Values*:

*For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load*

PEAK INVERSE VOLTAGE. . . . .	100 max.	volts
RMS SUPPLY VOLTAGE. . . . .	70 max.	volts
DC BLOCKING VOLTAGE. . . . .	100 max.	volts
AVERAGE FORWARD CURRENT:		
At case temperature of 135° C . . . . .	5 max.	amp
At other case temperatures. . . . .	See <i>Average-Forward-Current Rating Chart</i>	
PEAK RECURRENT CURRENT. . . . .	15 max.	amp
CASE-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +175	°C

#### Characteristics:

Maximum Forward Voltage Drop for dc forward amperes = 10, case temperature (°C) = 25.	1.5	volts
Maximum Reverse Current:		
Dynamic (Averaged over one complete cycle for maximum peak-reverse volts = 100, dc forward amperes = 5, case temperature (°C) = 150) . . . . .	1	ma
Static (DC value for maximum peak-reverse volts = 100, case temperature (°C) = 25). . . . .	0.01	ma



# 1N1613, 1N1613R

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OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHART,  
and  
CURVES

shown under Types 1N1612 and 1N1612R also apply to the  
1N1613 and 1N1613R



# 1N1614, 1N1614R

## Silicon Rectifiers

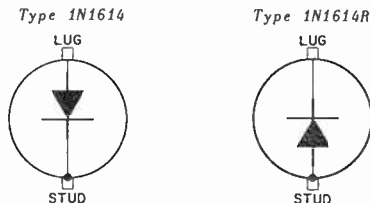
### DIFFUSED-JUNCTION TYPES

For Industrial and Military Power Supplies

#### GENERAL DATA

#### Mechanical:

Operating Position. . . . . Any  
 Dimensions. . . . . See *Dimensional Outline*  
 Dimensional Outline . . . . . JEDEC No. DO-4  
 Case. . . . . Metal  
 Seals . . . . . Hermetic  
 Terminal Diagrams (See *Dimensional Outline*):



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

#### HALF-WAVE RECTIFIER

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load

PEAK INVERSE VOLTAGE. . . . . 200 max. volts  
 RMS SUPPLY VOLTAGE. . . . . 140 max. volts  
 DC BLOCKING VOLTAGE . . . . . 200 max. volts

#### AVERAGE FORWARD CURRENT:

At case temperature of 135° C . . . . . 5 max. amp  
 At other case temperatures. . . See *Average-Forward-Current Rating Chart*

PEAK RECURRENT CURRENT. . . . . 15 max. amp

#### CASE-TEMPERATURE RANGE:

Operating and storage . . . . . -65 to +175 °C

#### Characteristics:

Maximum Forward Voltage Drop for dc forward amperes = 10, case temperature (°C) = 25 . . . 1.5 volts  
 Maximum Reverse Current:  
 Dynamic (Averaged over one complete cycle for maximum peak-reverse volts = 200, dc forward amperes = 5, case temperature (°C) = 150) . . . . . 1 ma  
 Static (DC value for maximum peak-reverse volts = 200, case temperature (°C) = 25) . . . . . 0.01 ma



# 1N1614, 1N1614R

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OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHART,  
and  
CURVES

shown under Types 1N1612 and 1N1612R also apply to the  
1N1614 and 1N1614R





# 1N1615, 1N1615R

## Silicon Rectifiers

### DIFFUSED-JUNCTION TYPES

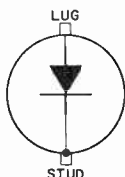
For Industrial and Military Power Supplies

#### GENERAL DATA

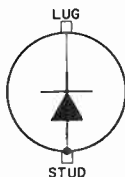
##### Mechanical:

Operating Position. . . . . Any  
 Dimensions. . . . . See *Dimensional Outline*  
 Dimensional Outline . . . . . JEDEC No. D0-4  
 Case. . . . . Metal  
 Seals . . . . . Hermetic  
 Terminal Diagrams (See *Dimensional Outline*):

Type 1N1615



Type 1N1615R



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

#### HALF-WAVE RECTIFIER

##### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load

PEAK INVERSE VOLTAGE. . . . .	400 max.	volts
RMS SUPPLY VOLTAGE. . . . .	280 max.	volts
DC BLOCKING VOLTAGE. . . . .	400 max.	volts
AVERAGE FORWARD CURRENT:		
At case temperature of 135° C . . . . .	5 max.	amp
At other case temperatures. . . . .	See <i>Average-Forward-Current Rating Chart</i>	
PEAK RECURRENT CURRENT. . . . .	15 max.	amp
CASE-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +175	°C

##### Characteristics:

Maximum Forward Voltage Drop for dc forward amperes = 10, case temperature (°C) = 25.	1.5	volts
Maximum Reverse Current:		
Dynamic (Averaged over one complete cycle for maximum peak-reverse volts = 400, dc forward amperes = 5, case temperature (°C) = 150) . . . . .	1	ma
Static (DC value for maximum peak-reverse volts = 400, case temperature (°C) = 25) . . . . .	0.01	ma



# 1N1615, 1N1615R

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OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHART,  
and  
CURVES

shown under Types 1N1612 and 1N1612R also apply to the  
1N1615 and 1N1615R



# 1N1616, 1N1616R

## Silicon Rectifiers

### DIFFUSED-JUNCTION TYPES

For Industrial and Military Power Supplies

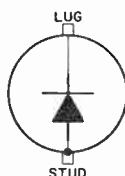
#### GENERAL DATA

##### Mechanical:

Operating Position. . . . . Any  
 Dimensions. . . . . See *Dimensional Outline*  
 Dimensional Outline. . . . . JEDEC No. DO-4  
 Case. . . . . Metal  
 Seals. . . . . Hermetic  
 Terminal Diagrams (See *Dimensional Outline*):

Type 1N1616

Type 1N1616R



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

#### HALF-WAVE RECTIFIER

##### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, and with resistive or inductive load

PEAK INVERSE VOLTAGE. . . . . 600 max. volts  
 RMS SUPPLY VOLTAGE. . . . . 420 max. volts  
 DC BLOCKING VOLTAGE. . . . . 600 max. volts

##### AVERAGE FORWARD CURRENT:

At case temperature of 135° C . . . . . 5 max. amp  
 At other case temperatures. . . See *Average-Forward-Current Rating Chart*

PEAK RECURRENT CURRENT. . . . . 15 max. amp

##### CASE-TEMPERATURE RANGE:

Operating and storage . . . . . -65 to +175 °C

##### Characteristics:

Maximum Forward Voltage Drop for dc forward amperes = 10, case temperature (°C) = 25. 1.5 volts

##### Maximum Reverse Current:

Dynamic (Averaged over one complete cycle for maximum peak-reverse volts = 600, dc forward amperes = 5, case temperature (°C) = 150) . . . . . 1 ma

Static (DC value for maximum peak-reverse volts = 600, case temperature (°C) = 25) . 0.01 ma



# 1N1616, 1N1616R

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OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHART,  
and  
CURVES

shown under Types 1N1612 and 1N1612R also apply to the  
1N1616 and 1N1616R



## Tunnel Diode

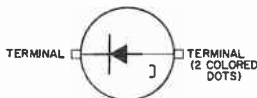
## GERMANIUM TYPE

A Low-Current Type for Applications Employing Clock (Pulse-Repetition) Rates up to 100 Mc with Typical Switching Times of 2 Millimicroseconds or Less

## GENERAL DATA

## Mechanical:

Operating Position . . . . .	Any
Maximum Overall Length . . . . .	0.265"
Maximum Width . . . . .	0.140"
Maximum Height . . . . .	0.055"
Case . . . . .	Metal and Ceramic
Colored Dots for Device Identification (See <i>Dimensional Outline</i> ) . . . . .	Red and Gray
Terminal Diagram (See <i>Dimensional Outline</i> ):	



The arrow indicates direction of forward current flow as indicated by dc ammeter.

## SWITCHING SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values*:

INSTANTANEOUS FORWARD CURRENT . . . . .	100 max.	ma
INSTANTANEOUS REVERSE CURRENT . . . . .	200 max.	ma
DISSIPATION: <sup>A</sup>		
At ambient temperature of 25° C . . . . .	40 max.	mw
AMBIENT-TEMPERATURE RANGE:		
Operating . . . . .	-65 to +150	°C
Storage . . . . .	-65 to +175	°C
CASE TEMPERATURE:		
For immersion in molten solder for 10 seconds maximum . . . . .	275 max.	°C

## Electrical Characteristics:

At ambient temperature of 25° C

		Min.	Typical	Max.	
Static:					
Peak-Point Current . . . . .	$I_P$	4.75	5	5.25	ma
Valley-Point Current . . . . .	$I_V$	-	0.45	0.6	ma
Peak-Point-to-Valley-Point Current Ratio . . . . .	$I_P/I_V$	8/1	11/1	-	
Peak-Point Voltage . . . . .	$V_P$	45	-	65	mV
Valley-Point Voltage . . . . .	$V_V$	280	-	330	mV
Positive Voltage at peak-point ma. = 5.25 . . . . .	$V_{F1}$	445	-	485	mV



# 1N3128

Min. Typical Max.

*Dynamic:*★

Terminal Valley-Point

Capacitance♦ . . . . .	C	-	7	15	μμf
Total Series Inductance . . . . .	L <sub>S</sub>	-	-	0.6	mμh
Total Series Resistance . . . . .	R <sub>S</sub>	-	-	1.5	ohms
Negative Resistance (-R <sub>D</sub> ) of Intrinsic Diode measured at inflection point of negative- resistance charac- teristic. . . . .	-R <sub>Dm</sub>	-	22	-	ohms
Dissipation with diode switched to its high- voltage state (V = V <sub>F1</sub> and I = I <sub>Pmax</sub> ). . . . .	P <sub>OPR</sub>	-	2.5	-	mw
Rise Time♣ . . . . .	t <sub>r</sub>	-	-	5	nμsec
Figure of Merit . . . . .	I <sub>P</sub> /C <sub>max</sub>	-	0.33	-	ma/μμf

▲ Derate linearly to 0 milliwatts at 150° C.

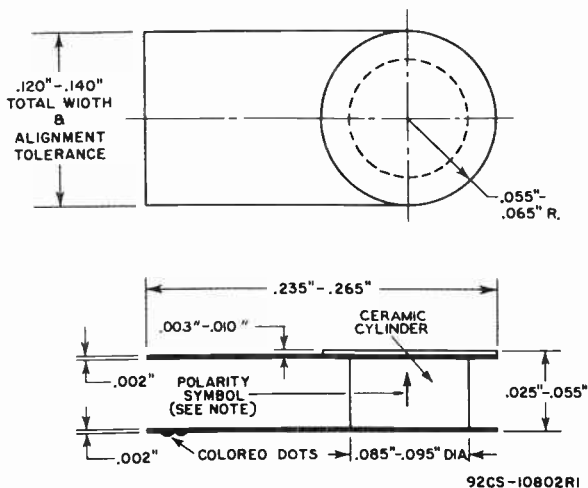
● See accompanying *Static-Forward-Characteristic* diagram.

★ See accompanying *Equivalent Circuit of a Tunnel Diode in the Negative-Resistance Region*.

♦ At measured I<sub>V</sub> for individual diode and includes case capacitance of 0.3 μμf.

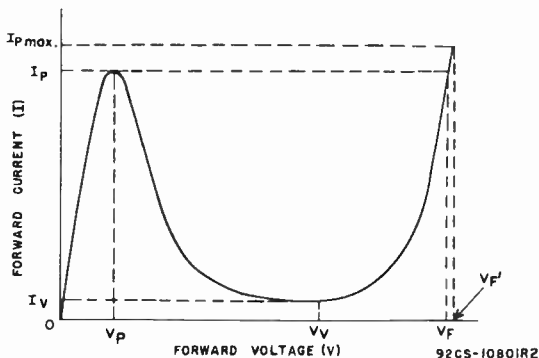
♣ The time required for the forward voltage to rise from V<sub>p</sub> + 0.1 (V<sub>F</sub> - V<sub>p</sub>) to V<sub>p</sub> + 0.9 (V<sub>F</sub> - V<sub>p</sub>). For 20 per cent overdrive (dc forward voltage and driving pulse provided by constant-current sources).



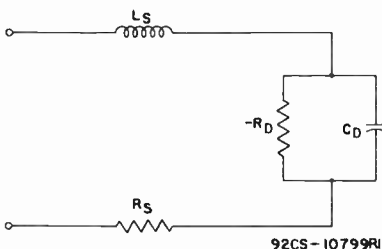


# 1N3128

## STATIC FORWARD CHARACTERISTIC OF A TUNNEL DIODE



## EQUIVALENT CIRCUIT OF A TUNNEL DIODE IN THE NEGATIVE-RESISTANCE REGION



- $L_s$  = TOTAL SERIES INDUCTANCE
- $R_s$  = TOTAL SERIES RESISTANCE
- $-R_d$  = NEGATIVE RESISTANCE OF INTRINSIC DIODE
- $C_d$  = BARRIER CAPACITANCE OF INTRINSIC DIODE



## Tunnel Diode

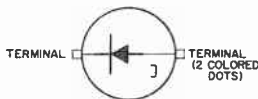
### GERMANIUM TYPE

An Intermediate-Speed Type for Applications Employing Clock (Pulse-Repetition) Rates up to 500 Mc with Typical Switching Times of 1/2 Millimicrosecond or Less

### GENERAL DATA

#### Mechanical:

Operating Position. . . . . Any  
 Maximum Overall Length. . . . . 0.265"  
 Maximum Width . . . . . 0.140"  
 Maximum Height. . . . . 0.055"  
 Case. . . . . Metal and Ceramic  
 Colored Dots for Device Identification (See *Dimensional Outline*). . . . . Red and White  
 Terminal Diagram (See *Dimensional Outline*):



The arrow indicates direction of forward current flow as indicated by dc ammeter.

### SWITCHING SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values*:

INSTANTANEOUS FORWARD CURRENT . . . . .	100 max.	ma
INSTANTANEOUS REVERSE CURRENT . . . . .	200 max.	ma
DISSIPATION: <sup>A</sup>		
At ambient temperature of 25° C . . . . .	40 max.	mw
AMBIENT-TEMPERATURE RANGE:		
Operating . . . . .	-65 to +150	°C
Storage . . . . .	-65 to +175	°C
CASE TEMPERATURE:		
For immersion in molten solder for 10 seconds maximum . . . . .	275 max.	°C

#### Electrical Characteristics:

At ambient temperature of 25° C

		Min.	Typical	Max.	
Static: <sup>B</sup>					
Peak-Point Current. . . . .	$I_P$	19	20	21	ma
Valley-Point Current. . . . .	$I_V$	-	1.8	2.4	ma
Peak-Point-to-Valley-Point Current Ratio . . . . .	$I_P/I_V$	8/1	11/1	-	
Peak-Point Voltage. . . . .	$V_P$	65	-	90	mv
Valley-Point Voltage. . . . .	$V_V$	300	-	360	mv
Positive Voltage at peak-point ma. = 21. . . . .	$V_{F'}$	500	-	550	mv



# 1N3129

Min. Typical Max.

*Dynamic:*★

Terminal Valley-Point

Capacitance♦ . . . . .	C	-	10	20	μμf
Total Series Inductance . . . . .	L <sub>S</sub>	-	-	0.6	nμh
Total Series Resistance . . . . .	R <sub>S</sub>	-	-	1.5	ohms
Negative Resistance (-R <sub>D</sub> ) of Intrinsic Diode measured at inflection point of negative-re- sistance characteristic	-R <sub>Dm</sub>	-	6	-	ohms
Dissipation with diode switched to its high- voltage state (V = V <sub>F</sub> , and I = I <sub>Pmax</sub> ) . . . . .	P <sub>OPR</sub>	-	12	-	mW
Rise Time↓ . . . . .	t <sub>r</sub>	-	-	2	nμSEC
Figure of Merit . . . . .	I <sub>P</sub> /C <sub>max</sub>	-	1	-	ma/μμf

▲ Derate linearly to 0 milliwatts at 150° C.

● See accompanying *Static-Forward-Characteristic* diagram.

★ See accompanying *Equivalent Circuit of a Tunnel Diode in the Negative-Resistance Region*.

♦ At measured by individual diode and includes case capacitance of 0.3 μμf.

↓ The time required for the forward voltage to rise from V<sub>p</sub> + 0.1(V<sub>F</sub> - V<sub>p</sub>) to V<sub>p</sub> + 0.9(V<sub>F</sub> - V<sub>p</sub>). For 20 per cent overdrive (dc forward voltage and driving pulse provided by constant-current sources).

DIMENSIONAL OUTLINE,  
STATIC FORWARD CHARACTERISTIC  
OF A TUNNEL DIODE,

and

EQUIVALENT CIRCUIT OF A TUNNEL DIODE  
IN THE NEGATIVE-RESISTANCE REGION

shown under Type 1N3128 also apply to the 1N3129



## Tunnel Diode

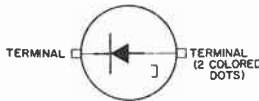
### GERMANIUM TYPE

An Ultra-High-Speed Type for Applications Employing Clock (Pulse-Repetition) Rates up to 1000 Mc with Typical Switching Times of 1/5 Millimicrosecond or Less

### GENERAL DATA

#### Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	0.265"
Maximum Width. . . . .	0.140"
Maximum Height. . . . .	0.055"
Case. . . . .	Metal and Ceramic
Colored Dots for Device Identification (See <i>Dimensional Outline</i> ). . . . .	Orange and Green
Terminal Diagram (See <i>Dimensional Outline</i> ):	



The arrow indicates direction of forward current flow as indicated by dc ammeter.

### SWITCHING SERVICE

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

INSTANTANEOUS FORWARD CURRENT. . . . .	100 max.	ma
INSTANTANEOUS REVERSE CURRENT. . . . .	200 max.	ma
DISSIPATION: <sup>▲</sup>		
At ambient temperature of 25° C. . . . .	40 max.	mw
AMBIENT-TEMPERATURE RANGE:		
Operating. . . . .	-65 to +150	°C
Storage. . . . .	-65 to +175	°C
CASE TEMPERATURE:		
For immersion in molten solder		
for 10 seconds maximum. . . . .	275 max.	°C

#### Electrical Characteristics:

At ambient temperature of 25° C

Min. Typical Max.

#### Static:

Peak-Point Current. . . . .	$I_P$	47.5	50	52.5	ma
Valley-Point Current. . . . .	$I_V$	-	4.5	6	ma
Peak-Point-to-Valley-Point Current Ratio. . . . .	$I_P/I_V$	8/1	11/1	-	
Peak-Point Voltage. . . . .	$V_P$	90	-	120	mv
Valley-Point Voltage. . . . .	$V_V$	350	-	430	mv
Positive Voltage at peak-point max. = 52.5. . . . .	$V_{P'}^1$	540	-	600	mv



# 1N3130

Min. Typical Max.

*Dynamic:*★

Terminal Valley-Point Capacitance . . . . .	C	-	12	25	$\mu\mu\text{f}$
Total Series Inductance.	$L_S$	-	-	0.6	$\pi\mu\text{h}$
Total Series Resistance.	$R_S$	-	-	1.2	ohms
Negative Resistance ( $-R_D$ ) of Intrinsic Diode measured at inflection point of negative-resistance characteristic. . . . .	$-R_{Dm}$	-	2.4	-	ohms
Dissipation with diode switched to its high-voltage state ( $V = V_F'$ and $I = I_{Pmax}$ ). . . . .	$P_{OPR}$	-	32	-	mw
Rise Time . . . . .	$t_r$	-	-	0.5	$\pi\mu\text{sec}$
Figure of Merit . . . . .	$I_p/C_{max}$	-	2	-	$\text{ma}/\mu\mu\text{f}$

▲ Derate linearly to 0 milliwatts at 150° C.

● See accompanying *Static-Forward-Characteristic* diagram.

★ See accompanying *Equivalent Circuit of a Tunnel Diode in the Negative-Resistance Region*.

◆ At measured  $I_V$  for individual diode and includes case capacitance of 0.3  $\mu\mu\text{f}$ .

↓ The time required for the forward voltage to rise from  $V_P + 0.1 (V_F - V_P)$  to  $V_P + 0.9 (V_F - V_P)$ . For 20 per cent overdrive (dc forward voltage and driving pulse provided by constant-current sources).

DIMENSIONAL OUTLINE,  
STATIC FORWARD CHARACTERISTIC  
OF A TUNNEL DIODE,

and

EQUIVALENT CIRCUIT OF A TUNNEL DIODE  
IN THE NEGATIVE-RESISTANCE REGION

shown under Type 1N312B also apply to the 1N3130



## Tunnel Diode

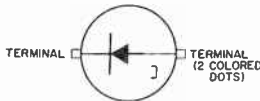
### GALLIUM-ARSENIDE TYPE

A High-Speed Type for Use as a Switching Device in Digital-Pulse Circuits and Memory Matrices, and in Other Applications Requiring Switching Times of  $1/2$  Millimicrosecond or Less and Clock (Pulse-Repetition) Rates up to 1000 Mc

### GENERAL DATA

#### Mechanical:

Operating Position . . . . .	Any
Maximum Overall Length . . . . .	0.265"
Maximum Width . . . . .	0.140"
Maximum Height . . . . .	0.055"
Case . . . . .	Metal and Ceramic
Colored Dots for Device Identification (See <i>Dimensional Outline</i> ) . . . . .	Yellow and Black
Terminal Diagram (See <i>Dimensional Outline</i> ):	



The arrow indicates direction of forward current flow as indicated by dc ammeter.

### SWITCHING SERVICE

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

INSTANTANEOUS FORWARD CURRENT . . . . .	100 max.	ma
INSTANTANEOUS REVERSE CURRENT . . . . .	200 max.	ma
DISSIPATION: <sup>▲</sup>		
At ambient temperature of 25° C . . . . .	75 max.	mw
AMBIENT-TEMPERATURE RANGE:		
Operating . . . . .	-65 to +150	°C
Storage . . . . .	-65 to +175	°C
CASE TEMPERATURE:		
For immersion in molten solder for 10 seconds maximum . . . . .	275 max.	°C

#### Electrical Characteristics:

At ambient temperature of 25° C

Min. Typical Max.

#### Static:<sup>\*</sup>

Peak-Point Current . . . . .	$I_P$	47.5	50	52.5	ma
Valley-Point Current . . . . .	$I_V$	-	2.5	3.5	ma
Peak-Point-to-Valley-Point Current Ratio . . . . .	$I_P/I_V$	13/1	20/1	-	
Peak-Point Voltage . . . . .	$V_P$	120	-	260	mv
Valley-Point Voltage . . . . .	$V_V$	510	-	620	mv



# IN3138

		Min.	Typical	Max.	
Positive Voltage at peak-point ma. = 52.5. . . .	$V_{F1}$	1100	-	1400	mv
<i>Dynamic:</i> ★					
Terminal Valley-Point Capacitance. . . . .	C	-	10	30	$\mu\mu\text{f}$
Total Series Inductance .	$L_S$	-	-	0.6	$\text{m}\mu\text{h}$
Total Series Resistance .	$R_S$	-	-	2.6	ohms
Negative Resistance ( $-R_D$ ) of Intrinsic Diode measured at inflection point of negative-resistance characteristic	$-R_{Dm}$	-	2.6	-	ohms
Dissipation with diode switched to its high-voltage state ( $V = V_{F1}$ and $I = I_{Pmax}$ ). . . . .	$P_{OPR}$	-	73	-	mw
Rise Time. . . . .	$t_r$	-	-	2	$\text{m}\mu\text{sec}$
Figure of Merit . . . . .	$I_P/2C_{max}$	-	0.9	-	$\text{ma}/\mu\mu\text{f}$

▲ Derate linearly to 0 milliwatts at 150° C.

● See accompanying *Static-Forward-Characteristic* diagram.

★ See accompanying *Equivalent Circuit of a Tunnel Diode in the Negative-Resistance Region*.

◆ At measured  $I_V$  for individual diode and includes case capacitance of 0.3  $\mu\mu\text{f}$ .

↓ The time required for the forward voltage to rise from  $V_P + 0.1(V_F - V_P)$  to  $V_P + 0.9(V_F - V_P)$ . For 20 per cent overdrive (dc forward voltage and driving pulse provided by constant-current sources).

**DIMENSIONAL OUTLINE,  
STATIC FORWARD CHARACTERISTIC  
OF A TUNNEL DIODE,**

and

**EQUIVALENT CIRCUIT OF A TUNNEL DIODE  
IN THE NEGATIVE-RESISTANCE REGION**

shown under Type IN3128 also apply to the IN3138



## Silicon Rectifier

### DIFFUSED-JUNCTION TYPE

For Industrial and Consumer-Product Applications

See also Insulated-Version Type 1N3253

### GENERAL DATA

#### Mechanical:

Operating Position. . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.405"
Maximum Diameter. . . . .	0.240"
Case. . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	2
Minimum length. . . . .	1.4"
Diameter. . . . .	0.027" to 0.035"
Orientation . . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps

	For resistive or inductive load	For capacitive- input filter	
PEAK INVERSE VOLTAGE. . . . .	200 max.	200 max.	volts
RMS SUPPLY VOLTAGE . . . . .	140 max.	70 max.	volts
FORWARD CURRENT: <sup>a</sup>			
DC . . . . .	750 max.	500 max.	ma
Peak recurrent . . . . .	-	6 max.	amp
Surge, for "turn- on" time of 2 milliseconds . . . . .	-	35 max.	amp
AMBIENT-TEMPERATURE RANGE:			
Operating. . . . .	-65 to +100		°C
Storage. . . . .	-65 to +175		°C



# 1N3193

## LEAD TEMPERATURE:

For 10 seconds maximum. . . . . 255 max. °C

## Characteristics:

*At ambient temperature of 25° C*

Minimum Instantaneous Forward Voltage

Drop at dc forward amperes = 0.5. . . . . 1.2 volts

Maximum Reverse Current at maximum

peak inverse voltage. . . . . 10  $\mu$ a

<sup>a</sup> At ambient temperatures up to 75° C. At ambient temperatures above 75° C see Rating Chart.

## OPERATING CONSIDERATIONS

A *surge-limiting impedance* should always be used in series with the rectifier. The impedance value must be sufficient to limit the surge current to the value specified under the maximum ratings. This impedance may be provided by the power-transformer windings, or by an external resistor or choke.

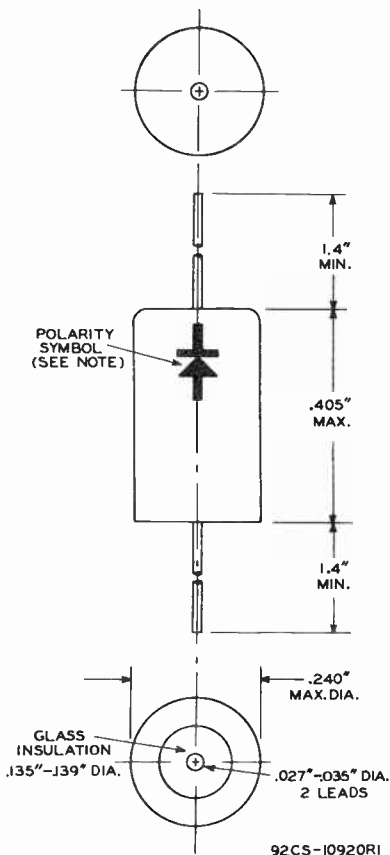
The *flexible leads* of this rectifier are usually soldered to the circuit elements. It is desirable in all soldering operations to provide some slack or an expansion elbow in the leads to prevent excessive tension on the leads. It is important during the soldering operation to avoid excessive heat in order to prevent possible damage to the rectifier. To absorb some of the heat, grip the flexible lead of the rectifier between the case and the soldering point with a pair of pliers.

When dip soldering is employed in the assembly of printed circuitry using this rectifier, the leads should not be dip soldered within 0.5" of the metal case.

Because the case of this rectifier may operate at voltages which are dangerous, care should be taken in the design of equipment to prevent the operator from coming in contact with the rectifier. It is recommended that this rectifier be mounted on the underside of the chassis.



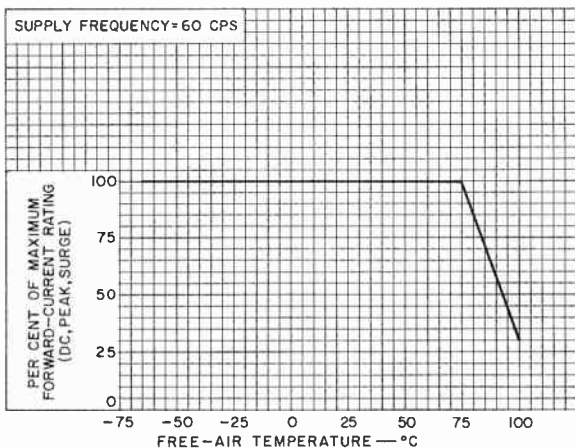




NOTE: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.

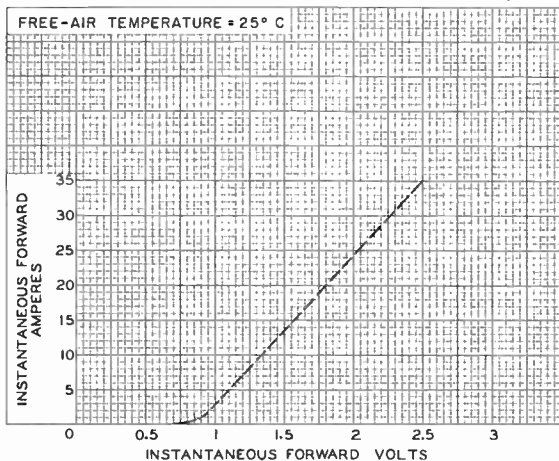


## RATING CHART



92CS-9727R2

## TYPICAL FORWARD CHARACTERISTIC



92CS-9730R2

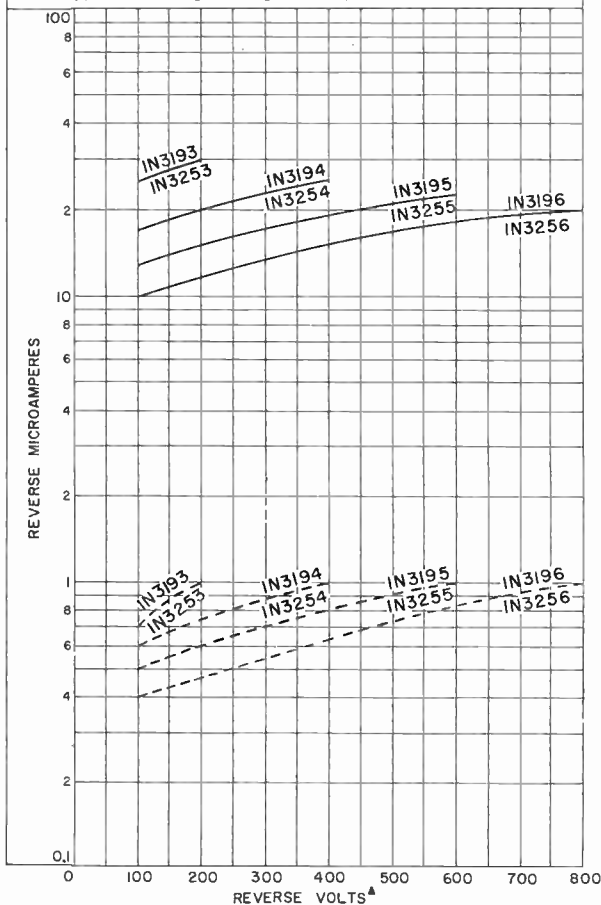


## TYPICAL REVERSE CHARACTERISTICS

▲ DO NOT EXCEED MAXIMUM PEAK-INVERSE-VOLTAGE RATING.

SOLID-LINE CURVES: DYNAMIC CHARACTERISTICS  
 MEASURED AT FREE-AIR TEMPERATURE = 75° C AND AT  
 MAXIMUM DC FORWARD-CURRENT RATING

DOTTED LINE CURVES: STATIC CHARACTERISTICS  
 MEASURED AT FREE-AIR TEMPERATURE = 25° C



92CM-1092IR1





## Silicon Rectifier

### DIFFUSED-JUNCTION TYPE

For Industrial and Consumer-Product Applications

#### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.405"
Maximum Diameter . . . . .	0.240"
Case . . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	2
Minimum length . . . . .	1.4"
Diameter . . . . .	0.027" to 0.035"
Orientation . . . . .	See <i>Dimensional Outline</i>

Terminal Diagram:



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps

	For resistive or inductive load	For capacitive- input filter	
PEAK INVERSE VOLTAGE . . . . .	200 max.	200 max.	volts
RMS SUPPLY VOLTAGE . . . . .	140 max.	70 max.	volts
FORWARD CURRENT: <sup>a</sup>			
DC . . . . .	750 max.	500 max.	ma
Peak recurrent . . . . .	-	6 max.	amp
Surge, for "turn- on" time of 2 milliseconds . . . . .	-	35 max.	amp
AMBIENT-TEMPERATURE RANGE:			
Operating . . . . .	-65 to +100		°C
Storage . . . . .	-65 to +175		°C
LEAD TEMPERATURE:			
For 10 seconds maximum . . . . .	255 max.		°C



# 1N3193

## Characteristics:

At ambient temperature of 25° C

Minimum Instantaneous Forward Voltage	
Drop at dc forward amperes = 0.5 . . . . .	1.2 volts
Maximum Reverse Current at maximum peak inverse voltage . . . . .	10 $\mu$ a

<sup>a</sup> At ambient temperatures up to 75° C. At ambient temperatures above 75° C see *Rating Chart*.

## OPERATING CONSIDERATIONS

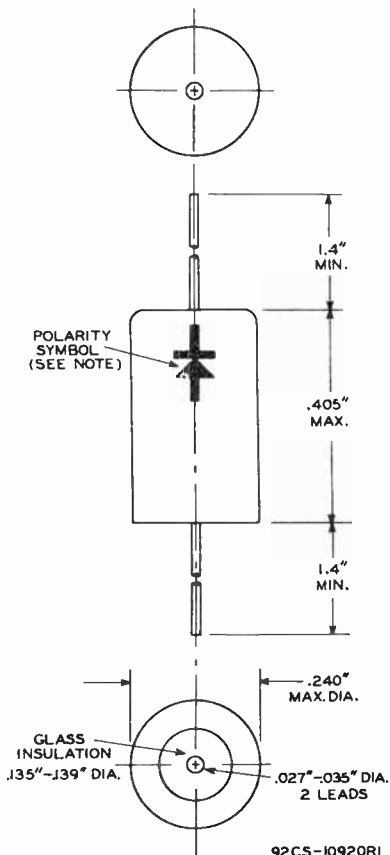
A *surge-limiting impedance* should always be used in series with the rectifier. The impedance value must be sufficient to limit the surge current to the value specified under the maximum ratings. This impedance may be provided by the power-transformer windings, or by an external resistor or choke.

The *flexible leads* of this rectifier are usually soldered to the circuit elements. It is desirable in all soldering operations to provide some slack or an expansion elbow in the leads to prevent excessive tension on the leads. It is important during the soldering operation to avoid excessive heat in order to prevent possible damage to the rectifier. To absorb some of the heat, grip the flexible lead of the rectifier between the case and the soldering point with a pair of pliers.

When dip soldering is employed in the assembly of printed circuitry using this rectifier, the leads should not be dip soldered within 0.5" of the metal case.

Because the case of this rectifier may operate at voltages which are dangerous, care should be taken in the design of equipment to prevent the operator from coming in contact with the rectifier. It is recommended that this rectifier be mounted on the underside of the chassis.



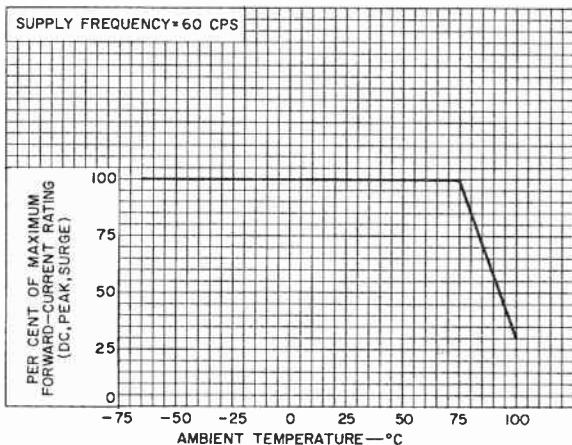


NOTE: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.



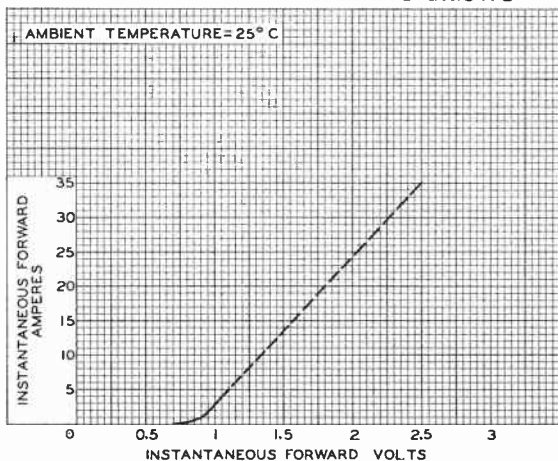
# 1N3193

## RATING CHART



92CS-9727RI

## TYPICAL FORWARD CHARACTERISTIC



92CS-9730



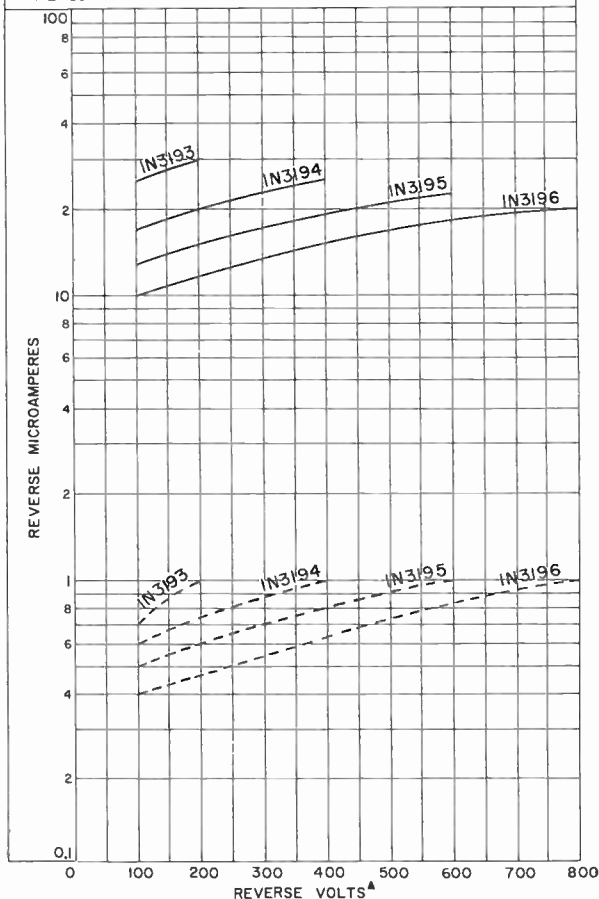


## TYPICAL REVERSE CHARACTERISTICS

▲ DO NOT EXCEED MAXIMUM PEAK-INVERSE-VOLTAGE RATING.

SOLID-LINE CURVES: DYNAMIC CHARACTERISTICS  
 MEASURED AT AMBIENT TEMPERATURE = 75° C AND AT  
 MAXIMUM DC-FORWARD-CURRENT RATING

DOTTED LINE CURVES: STATIC CHARACTERISTICS  
 MEASURED AT AMBIENT TEMPERATURE = 25° C



92CM-10921





## Silicon Rectifier

### DIFFUSED-JUNCTION TYPE

For Industrial and Consumer-Product Applications

See also Insulated-Version Type 1N3254

### GENERAL DATA

#### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.405"
Maximum Diameter . . . . .	0.240"
Case . . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	2
Minimum length . . . . .	1.4"
Diameter . . . . .	0.027" to 0.035"
Orientation . . . . .	See <i>Dimensional Outline</i>

Terminal Diagram:



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

Maximum and Minimum Ratings, *Absolute-Maximum Values:*

*For power-supply frequency of 60 cps*

	<i>For resistive or inductive load</i>	<i>For capacitive- input filter</i>	
PEAK INVERSE VOLTAGE . . . . .	400 max.	400 max.	volts
RMS SUPPLY VOLTAGE . . . . .	280 max.	140 max.	volts
FORWARD CURRENT: <sup>a</sup>			
DC . . . . .	750 max.	500 max.	ma
Peak recurrent . . . . .	-	6 max.	amp
Surge, for "turn- on" time of 2 milliseconds . . . . .	-	35 max.	amp
AMBIENT-TEMPERATURE RANGE:			
Operating . . . . .	-65 to +100		°C
Storage . . . . .	-65 to +175		°C



# 1N3194

## LEAD TEMPERATURE:

For 10 seconds maximum. . . . . 255 max. °C

## Characteristics:

*At ambient temperature of 25° C*

Minimum Instantaneous Forward Voltage

Drop at dc forward amperes = 0.5. . . . . 1.2 volts

Maximum Reverse Current at maximum

peak inverse voltage. . . . . 10  $\mu$ a

<sup>a</sup> At ambient temperatures up to 75° C. At ambient temperatures above 75° C see *Rating Chart*.

## OPERATING CONSIDERATIONS

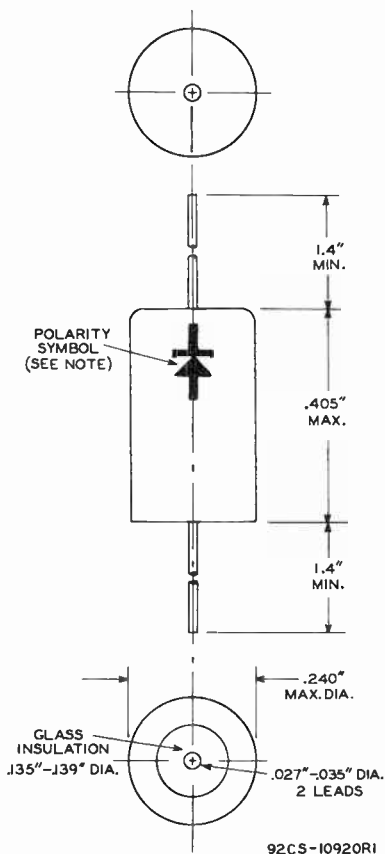
A *surge-limiting impedance* should always be used in series with the rectifier. The impedance value must be sufficient to limit the surge current to the value specified under the maximum ratings. This impedance may be provided by the power-transformer windings, or by an external resistor or choke.

The *flexible leads* of this transistor are usually soldered to the circuit elements. It is desirable in all soldering operations to provide some slack or an expansion elbow in the leads to prevent excessive tension on the leads. It is important during the soldering operation to avoid excessive heat in order to prevent possible damage to the rectifier. To absorb some of the heat, grip the flexible lead of the rectifier between the case and the soldering point with a pair of pliers.

When dip soldering is employed in the assembly of printed circuitry using this rectifier, the leads should not be dip soldered within 0.5" of the metal case.

Because the case of this rectifier may operate at voltages which are dangerous, care should be taken in the design of equipment to prevent the operator from coming in contact with the rectifier. It is recommended that this rectifier be mounted on the underside of the chassis.

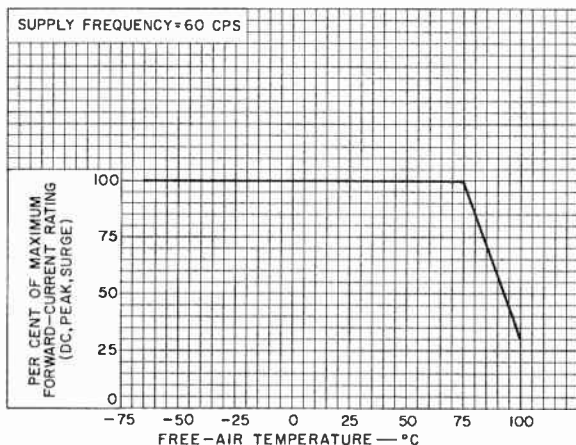




NOTE: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.

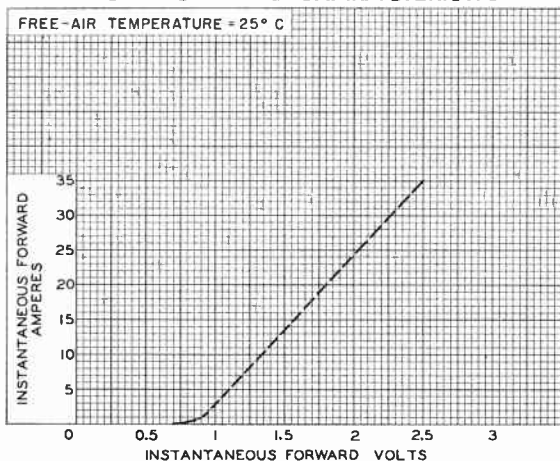


## RATING CHART



92CS-9727R2

## TYPICAL FORWARD CHARACTERISTIC



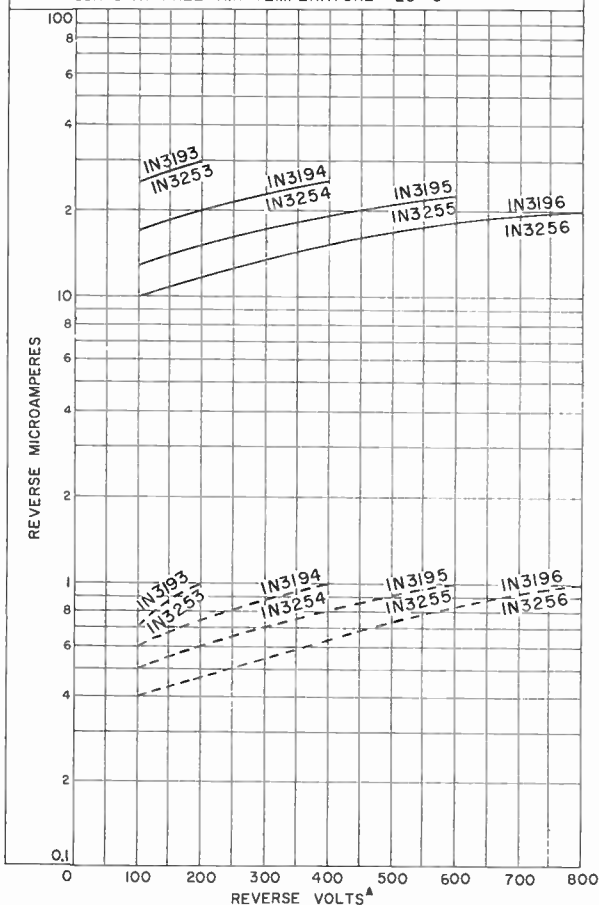
92CS-9730R2

## TYPICAL REVERSE CHARACTERISTICS

▲ DO NOT EXCEED MAXIMUM PEAK-INVERSE-VOLTAGE RATING.

SOLID-LINE CURVES: DYNAMIC CHARACTERISTICS  
MEASURED AT FREE-AIR TEMPERATURE = 75° C AND AT  
MAXIMUM DC FORWARD-CURRENT RATING

DOTTED LINE CURVES: STATIC CHARACTERISTICS  
MEASURED AT FREE-AIR TEMPERATURE = 25° C



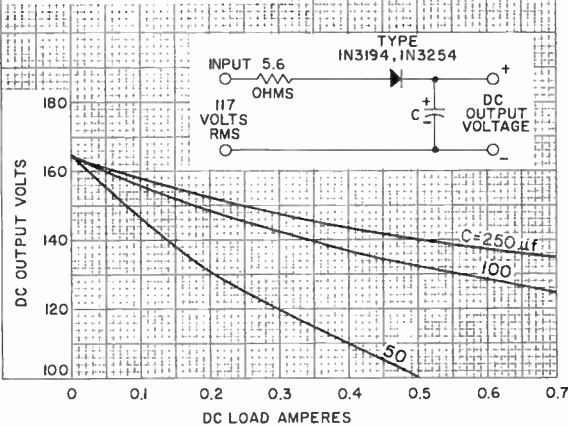
92CM-1092IRI



# IN3194

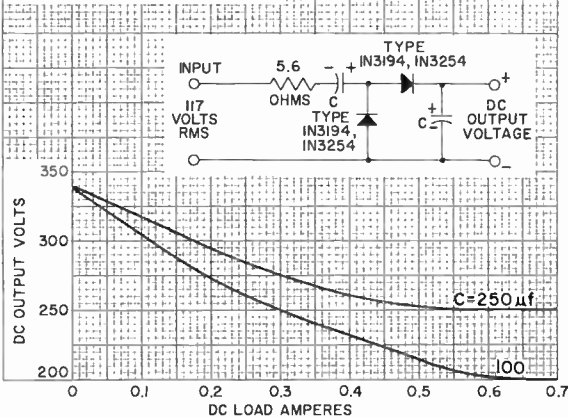
## TYPICAL OPERATION CHARACTERISTICS Half-Wave Rectifier

FREE-AIR TEMPERATURE = 25° C  
SUPPLY FREQUENCY = 60 CPS



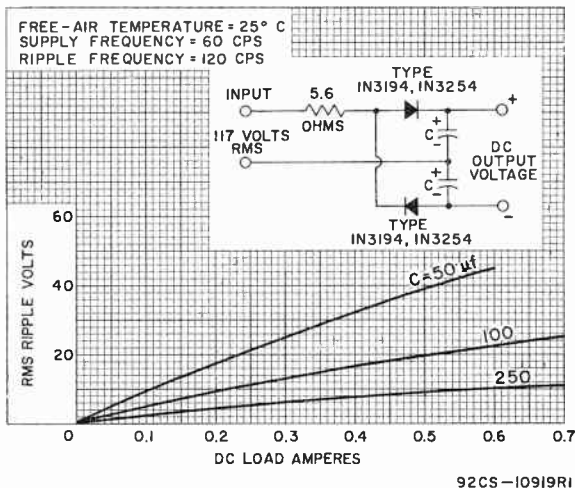
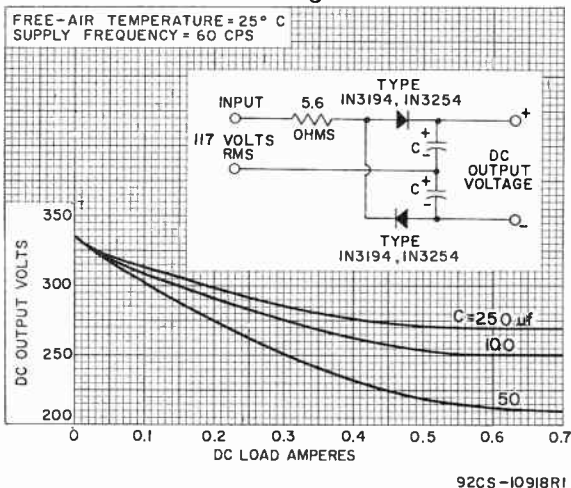
## Half-Wave Voltage Doubler

FREE-AIR TEMPERATURE = 25° C  
SUPPLY FREQUENCY = 60 CPS





## TYPICAL OPERATION CHARACTERISTICS Full-Wave Voltage Doubler





## Silicon Rectifier

## DIFFUSED-JUNCTION TYPE

For Industrial and Consumer-Product Applications

## Mechanical:

Operating Position. . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.405"
Maximum Diameter. . . . .	0.240"
Case. . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	2
Minimum length. . . . .	1.4"
Diameter. . . . .	0.027" to 0.035"
Orientation . . . . .	See <i>Dimensional Outline</i>

Terminal Diagram:



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

## HALF-WAVE RECTIFIER

Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps

	For resistive or inductive load	For capacitive- input filter	
PEAK INVERSE VOLTAGE. . . . .	400 max.	400 max.	volts
RMS SUPPLY VOLTAGE. . . . .	280 max.	140 max.	volts
FORWARD CURRENT: <sup>a</sup>			
DC. . . . .	750 max.	500 max.	ma
Peak recurrent. . . . .	-	6 max.	amp
Surge, for "turn- on" time of 2 milliseconds. . . . .	-	35 max.	amp
AMBIENT-TEMPERATURE RANGE:			
Operating . . . . .	-65 to +100		°C
Storage . . . . .	-65 to +175		°C
LEAD TEMPERATURE:			
For 10 seconds maximum . . . . .	255 max.		°C

<sup>a</sup> At ambient temperatures up to 75°C. At ambient temperatures above 75°C see Rating Chart.



# 1N3194

## Characteristics:

*At ambient temperature of 25° C*

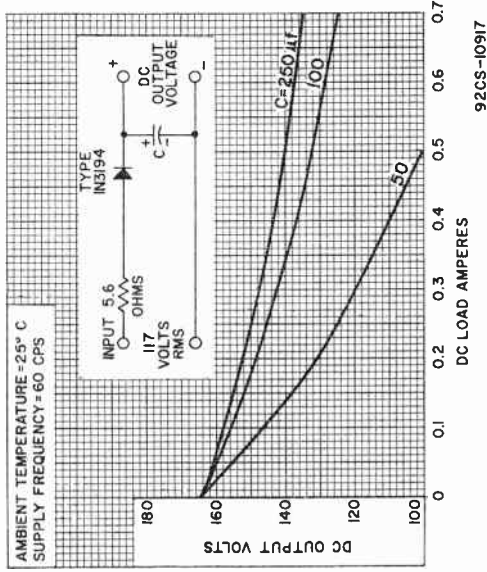
Maximum Instantaneous Forward Voltage	
Drop at dc forward amperes = 0.5. . . . .	1.2 volts
Maximum Reverse Current at maximum peak inverse voltage. . . . .	10 $\mu$ a

OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
RATING CHART,  
TYPICAL-FORWARD-CHARACTERISTIC CURVE,  
and  
TYPICAL-REVERSE-CHARACTERISTICS CURVE  
(Given on multitype curve sheet)  
shown under Type 1N3193 also apply to the 1N3194

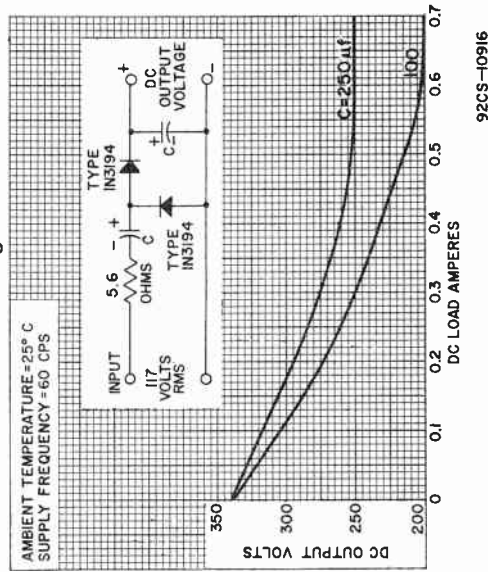


## TYPICAL OPERATION CHARACTERISTICS

### Half-Wave Rectifier

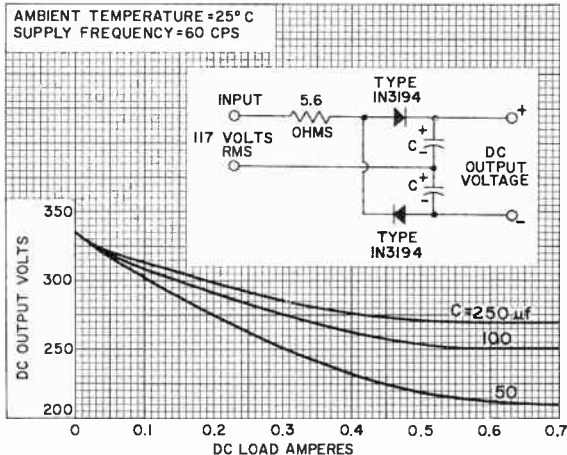


## Half-Wave Voltage Doubler

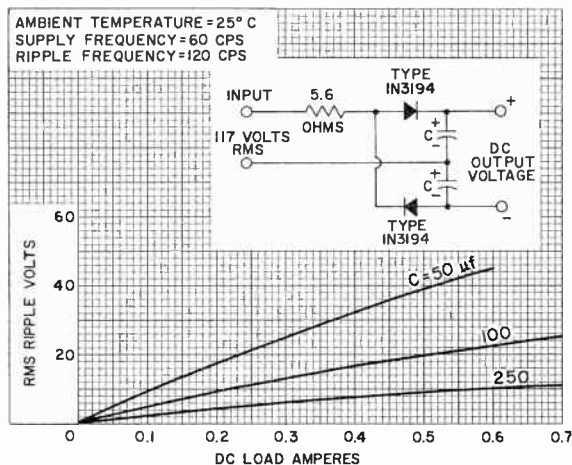


# 1N3194

## TYPICAL OPERATION CHARACTERISTICS Full-Wave Voltage Doubler



92CS-10918



92CS-10919

## Silicon Rectifier

### DIFFUSED-JUNCTION TYPE

For Industrial and Consumer-Product Applications

See also Insulated-Version Type 1N3255

### GENERAL DATA

#### Mechanical:

Operating Position. . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.405"
Maximum Diameter. . . . .	0.240"
Case. . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	2
Minimum length. . . . .	1.4"
Diameter. . . . .	0.027" to 0.035"
Orientation . . . . .	See <i>Dimensional Outline</i>

#### Terminal Diagram:



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

Maximum and Minimum Ratings, *Absolute-Maximum Values:*

*For power-supply frequency of 60 cps*

	<i>For resistive or inductive load</i>	<i>For capacitive- input filter</i>	
--	--	---	--

PEAK INVERSE VOLTAGE. . . . .	600 max.	600 max.	volts
RMS SUPPLY VOLTAGE . . . . .	420 max.	210 max.	volts
FORWARD CURRENT: <sup>a</sup>			
DC . . . . .	750 max.	500 max.	ma
Peak recurrent . . . . .	-	6 max.	amp
Surge, for "turn- on" time of 2 milliseconds . . . . .	-	35 max.	amp
AMBIENT-TEMPERATURE RANGE:			
Operating. . . . .	-65 to +100		°C
Storage. . . . .	-65 to +175		°C



# 1N3195

## LEAD TEMPERATURE:

For 10 seconds maximum. . . . . 255 max. °C

## Characteristics:

*At ambient temperature of 25° C*

Minimum Instantaneous Forward Voltage

Drop at dc forward amperes = 0.5. . . . . 1.2 volts

Maximum Reverse Current at maximum

peak inverse voltage. . . . . 10  $\mu$ a

<sup>a</sup> At ambient temperatures up to 75° C. At ambient temperatures above 75° C see Rating Chart.

## OPERATING CONSIDERATIONS

A surge-limiting impedance should always be used in series with the rectifier. The impedance value must be sufficient to limit the surge current to the value specified under the maximum ratings. This impedance may be provided by the power-transformer windings, or by an external resistor or choke.

The flexible leads of this transistor are usually soldered to the circuit elements. It is desirable in all soldering operations to provide some slack or an expansion elbow in the leads to prevent excessive tension on the leads. It is important during the soldering operation to avoid excessive heat in order to prevent possible damage to the rectifier. To absorb some of the heat, grip the flexible lead of the rectifier between the case and the soldering point with a pair of pliers.

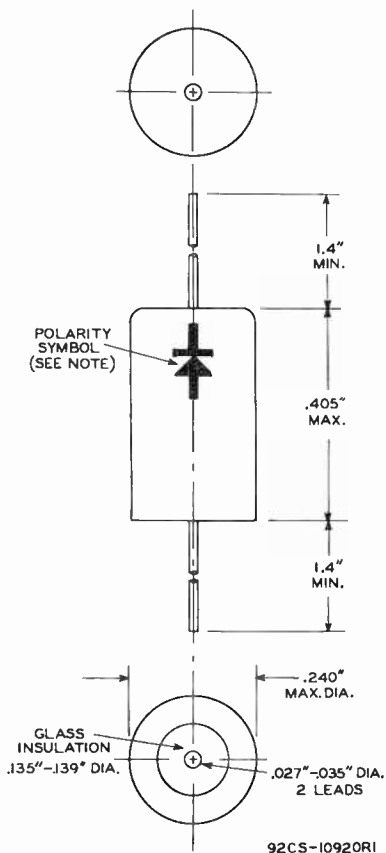
When dip soldering is employed in the assembly of printed circuitry using this rectifier, the leads should not be dip soldered within 0.5" of the metal case.

Because the case of this rectifier may operate at voltages which are dangerous, care should be taken in the design of equipment to prevent the operator from coming in contact with the rectifier. It is recommended that this rectifier be mounted on the underside of the chassis.





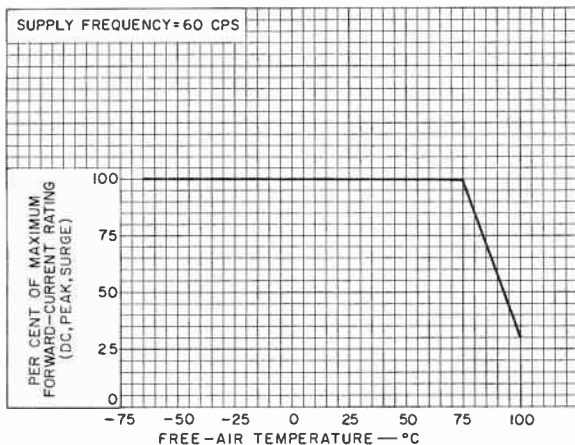
# 1N3195



NOTE: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.

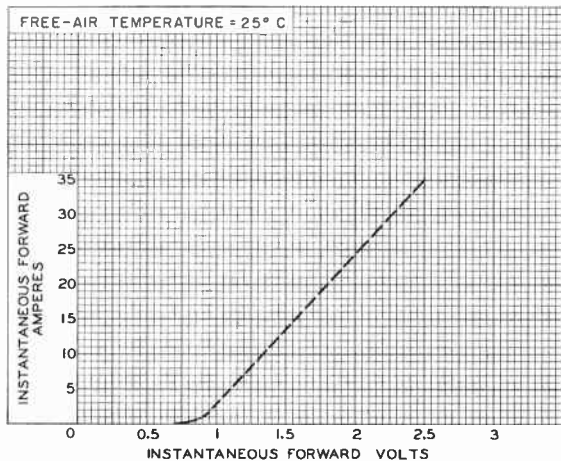


## RATING CHART



92CS-9727R2

## TYPICAL FORWARD CHARACTERISTIC



92CS-9730R2

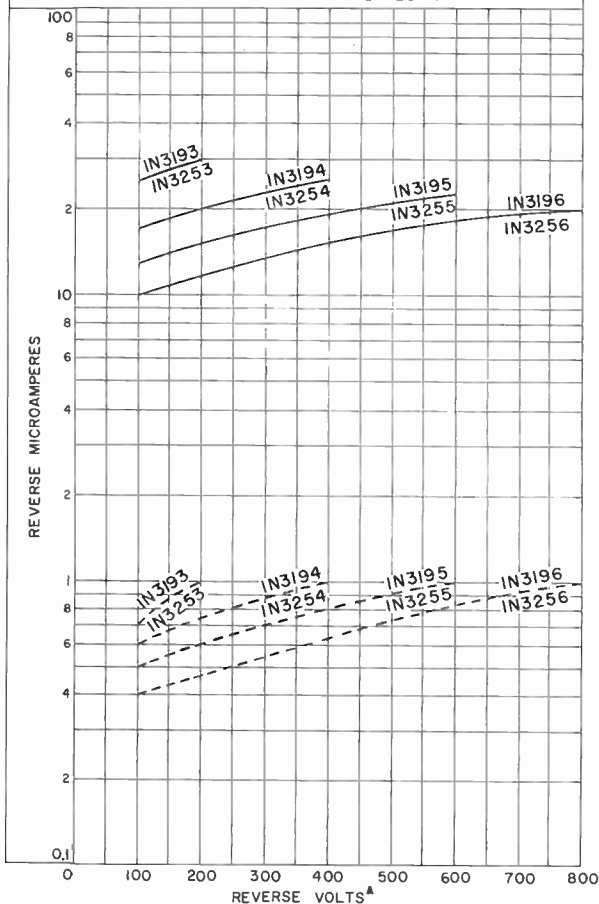


## TYPICAL REVERSE CHARACTERISTICS

▲ DO NOT EXCEED MAXIMUM PEAK-INVERSE-VOLTAGE RATING.

SOLID-LINE CURVES: DYNAMIC CHARACTERISTICS  
MEASURED AT FREE-AIR TEMPERATURE = 75° C AND AT  
MAXIMUM DC FORWARD-CURRENT RATING

DOTTED LINE CURVES: STATIC CHARACTERISTICS  
MEASURED AT FREE-AIR TEMPERATURE = 25° C



92CM-1092IR1





## Silicon Rectifier

### DIFFUSED-JUNCTION TYPE

For Industrial and Consumer-Product Applications

#### Mechanical:

Operating Position. . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.405"
Maximum Diameter. . . . .	0.240"
Case. . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	2
Minimum length. . . . .	1.4"
Diameter. . . . .	0.027" to 0.035"
Orientation . . . . .	See <i>Dimensional Outline</i>

#### Terminal Diagram:



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps

	For resistive or inductive load	For capacitive- input filter	
PEAK INVERSE VOLTAGE.	600 max.	600 max.	volts
RMS SUPPLY VOLTAGE. . .	420 max.	210 max.	volts
FORWARD CURRENT: <sup>a</sup>			
DC. . . . .	750 max.	500 max.	ma
Peak recurrent. . .	-	6 max.	amp
Surge, for "turn-on" time of 2 milli- seconds . . . . .	-	35 max.	amp
AMBIENT-TEMPERATURE RANGE:			
Operating . . . . .	-65 to +100		°C
Storage . . . . .	-65 to +175		°C
LEAD TEMPERATURE:			
For 10 seconds maximum . . . . .	255 max.		°C



# 1N3195

## Characteristics:

*At ambient temperature of 25° C*

Maximum Instantaneous Forward

Voltage Drop at dc forward amperes = 0.5. . . . . 1.2 volts

Maximum Reverse Current at maximum

peak inverse voltage. . . . . 10  $\mu$ a

<sup>a</sup> At ambient temperatures up to 75° C. At ambient temperatures above 75° C see *Rating Chart*.

OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
RATING CHART,  
TYPICAL-FORWARD-CHARACTERISTIC CURVE,  
and  
TYPICAL-REVERSE-CHARACTERISTICS CURVE  
(Given on multitype curve sheet)  
shown under Type 1N3193 also apply to the 1N3195



## Silicon Rectifier

### DIFFUSED-JUNCTION TYPE

For Industrial and Consumer-Product Applications

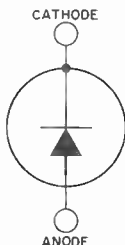
See also Insulated-Version Type 1N3256

### GENERAL DATA

#### Mechanical:

Operating Position. . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.405"
Maximum Diameter. . . . .	0.240"
Case. . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	2
Minimum length. . . . .	1.4"
Diameter. . . . .	0.027" to 0.035"
Orientation . . . . .	See <i>Dimensional Outline</i>

Terminal Diagram:



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

Maximum and Minimum Ratings, Absolute-Maximum Values:

*For power-supply frequency of 60 cps*

*For resistive or inductive load      For capacitive-input filter*

PEAK INVERSE VOLTAGE. . . . .	800 max.	800 max.	volts
RMS SUPPLY VOLTAGE. . . . .	560 max.	280 max.	volts
FORWARD CURRENT: <sup>a</sup>			
DC. . . . .	500 max.	400 max.	ma
Peak recurrent. . . . .	-	5 max.	amp
Surge, for "turn-on" time of 2 milliseconds. . . . .	-	35 max.	amp
AMBIENT-TEMPERATURE RANGE:			
Operating . . . . .	-65 to +100		°C
Storage . . . . .	-65 to +175		°C



# 1N3196

## LEAD TEMPERATURE:

For 10 seconds

maximum . . . . .

255 max.

°C

## Characteristics:

*At ambient temperature of 25° C*

Minimum Instantaneous Forward Voltage

Drop at dc forward amperes = 0.5. . . . . 1.2 volts

Maximum Reverse Current at maximum

peak inverse voltage. . . . . 10  $\mu$ a

<sup>a</sup> At ambient temperatures up to 75° C. At ambient temperatures above 75° C see Rating Chart.

## OPERATING CONSIDERATIONS

A surge-limiting impedance should always be used in series with the rectifier. The impedance value must be sufficient to limit the surge current to the value specified under the maximum ratings. This impedance may be provided by the power transformer windings, or by an external resistor or choke.

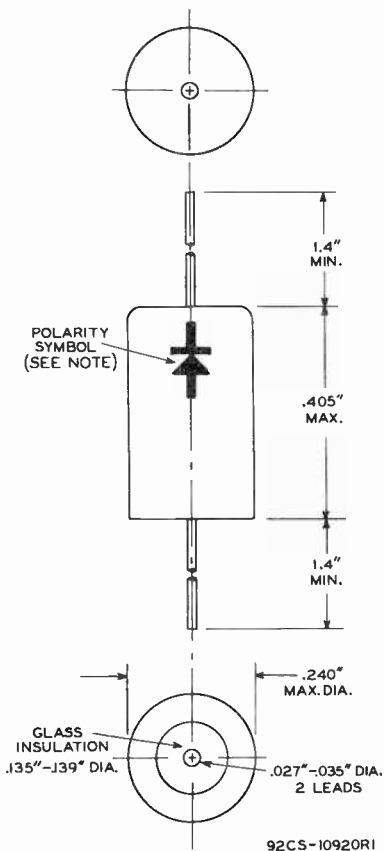
The flexible leads of this rectifier are usually soldered to the circuit elements. It is desirable in all soldering operations to provide some slack or an expansion elbow in the leads to prevent excessive tension on the leads. It is important during the soldering operation to avoid excessive heat in order to prevent possible damage to the rectifier. To absorb some of the heat, grip the flexible lead of the rectifier between the case and the soldering point with a pair of pliers.

When dip soldering is employed in the assembly of printed circuitry using this rectifier, the leads should not be dip soldered within 0.5" of the metal case.

Because the case of this rectifier may operate at voltages which are dangerous, care should be taken in the design of equipment to prevent the operator from coming in contact with the rectifier. It is recommended that this rectifier be mounted on the underside of the chassis.



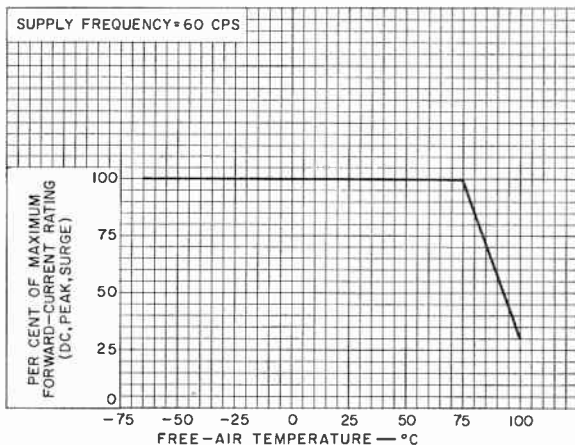




NOTE: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.

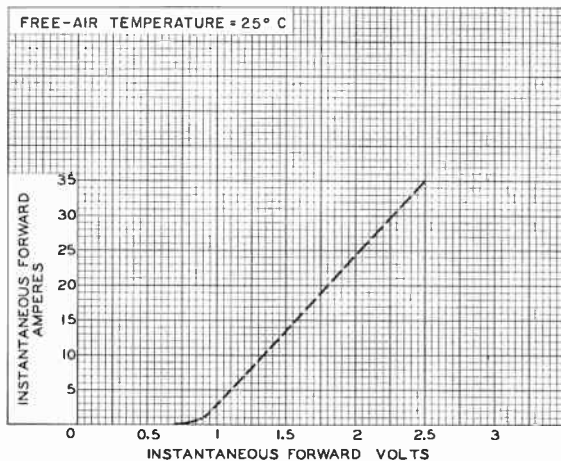


## RATING CHART



92CS-9727R2

## TYPICAL FORWARD CHARACTERISTIC



92CS-9730R2

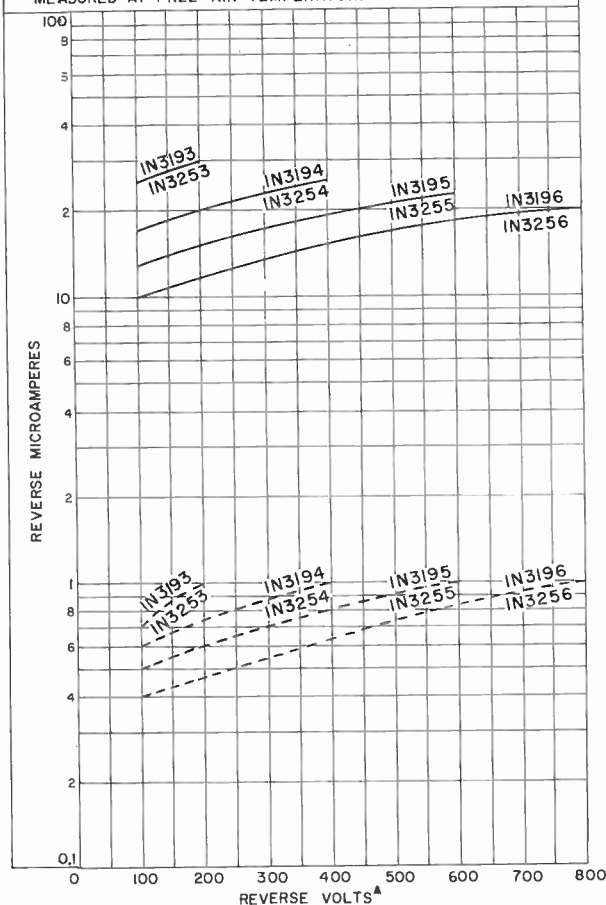


## TYPICAL REVERSE CHARACTERISTICS

▲ DO NOT EXCEED MAXIMUM PEAK-INVERSE-VOLTAGE RATING.

SOLID-LINE CURVES: DYNAMIC CHARACTERISTICS  
 MEASURED AT FREE-AIR TEMPERATURE = 75° C AND AT  
 MAXIMUM DC FORWARD-CURRENT RATING

DOTTED LINE CURVES: STATIC CHARACTERISTICS  
 MEASURED AT FREE-AIR TEMPERATURE = 25° C

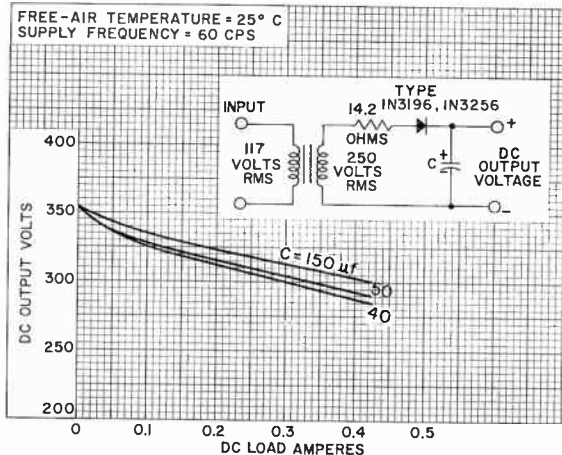


92CM-10921R1



# 1N3196

## TYPICAL OPERATION CHARACTERISTICS Half-Wave Rectifier



92CS-10915R1

## Silicon Rectifier

### DIFFUSED-JUNCTION TYPE

For Industrial and Consumer-Product Applications

#### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.405"
Maximum Diameter . . . . .	0.240"
Case . . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	2
Minimum length . . . . .	1.4"
Diameter . . . . .	0.027" to 0.035"
Orientation . . . . .	See <i>Dimensional Outline</i>

#### Terminal Diagram:



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps

	For resistive or inductive load	For capacitive- input filter	
PEAK INVERSE VOLTAGE . . . . .	800 max.	800 max.	volts
RMS SUPPLY VOLTAGE . . . . .	560 max.	280 max.	volts
FORWARD CURRENT: <sup>a</sup>			
DC . . . . .	500 max.	400 max.	ma
Peak recurrent . . . . .	-	5 max.	amp
Surge, for "turn- on" time of 2 milliseconds . . . . .	-	35 max.	amp
AMBIENT-TEMPERATURE RANGE:			
Operating . . . . .	-65 to +100		°C
Storage . . . . .	-65 to +175		°C
LEAD TEMPERATURE:			
For 10 seconds maximum . . . . .	255 max.		°C

<sup>a</sup> At ambient temperatures up to 75° C. At ambient temperatures above 75° C see *Rating Chart*.



# 1N3196

## Characteristics:

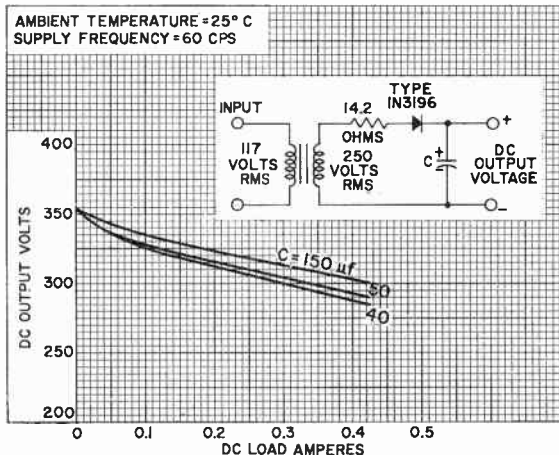
At ambient temperature of 25° C

Maximum Instantaneous Forward Voltage Drop at dc forward amperes = 0.4 . . . . .	1.2 volts
Maximum Reverse Current at maximum peak inverse voltage. . . . .	10 $\mu$ a

OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
RATING CHART,  
TYPICAL-FORWARD-CHARACTERISTIC CURVE,  
and  
TYPICAL-REVERSE-CHARACTERISTICS CURVE

(Given on multitype curve sheet)  
shown under Type 1N3193 also apply to the 1N3196

## TYPICAL OPERATION CHARACTERISTICS Half-Wave Rectifier



92CS-10915



# 1N3253

## Silicon Rectifier

DIFFUSED-JUNCTION TYPE

For Industrial and Consumer-Product Applications

See also Uninsulated-Version Type 1N3193

*The 1N3253 is the same as the 1N3193 except for the following items:*

**Mechanical:**

Case. . . . . Metal with Insulating Sleeve<sup>a</sup>

# 1N3254

## Silicon Rectifier

DIFFUSED-JUNCTION TYPE

For Industrial and Consumer-Product Applications

See also Uninsulated-Version Type 1N3194

*The 1N3254 is the same as the 1N3194 except for the following items:*

**Mechanical:**

Case. . . . . Metal with Insulating Sleeve<sup>a</sup>

# 1N3255

## Silicon Rectifier

DIFFUSED-JUNCTION TYPE

For Industrial and Consumer-Product Applications

See also Uninsulated-Version Type 1N3195

*The 1N3255 is the same as the 1N3195 except for the following items:*

**Mechanical:**

Case. . . . . Metal with Insulating Sleeve<sup>a</sup>

<sup>a</sup> The maximum diameter of the metal case with insulating sleeve is 0.240". The specifications of the insulating sleeve are: material, plastic; wall thickness, 0.002"; dielectric strength, 4500 volts/mil at 25° C, 3150 volts/mil at 150° C; moisture absorption, 0.3% (surface resistivity is not affected by moisture); degree of transparency, optically clear.



# 1N3256

## Silicon Rectifier

DIFFUSED-JUNCTION TYPE

For Industrial and Consumer-Product Applications

See also Uninsulated-Version Type 1N3196

*The 1N3256 is the same as the 1N3196 except for the following items:*

### Mechanical:

Case. . . . . Metal with Insulating Sleeve<sup>a</sup>

<sup>a</sup> The maximum diameter of the metal case with insulating sleeve is 0.240". The specifications of the insulating sleeve are: material, plastic; wall thickness, 0.002"; dielectric strength, 4500 volts/mil at 25° C, 3150 volts/mil at 150° C; moisture absorption, 0.3% (surface resistivity is not affected by moisture); degree of transparency, optically clear.





## Silicon Rectifier

### DIFFUSED-JUNCTION TYPE

For Industrial and Consumer-Product Applications

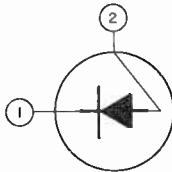
#### GENERAL DATA

##### Mechanical:

Dimensions. . . . . Similar to Outline TO-1 in General Section except that lead 3 is omitted

##### Terminal Diagram:

BOTTOM VIEW



Lead 1 - Cathode

Lead 2 - Anode

The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

#### HALF-WAVE RECTIFIER

##### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps  
and for capacitor-input filter

PEAK REVERSE VOLTAGE. . . . .	100 max.	volts
RMS SUPPLY VOLTAGE. . . . .	35 max.	volts
FORWARD CURRENT: <sup>a</sup>		
DC. . . . .	125 max.	ma
Peak recurrent. . . . .	1.3 max.	amp
Surge, for "turn-on" time of 2 milliseconds. . . . .	30 max.	amp
FREE-AIR TEMPERATURE RANGE:		
Operating. . . . .	-65 to +100	°C
Storage. . . . .	-65 to +175	°C
LEAD TEMPERATURE:		
For 10 seconds maximum. . . . .	255 max.	°C

##### Characteristics:

At free-air temperature of 25° C unless otherwise specified

##### Maximum Instantaneous Forward Voltage

Drop at dc forward ma. = 125. . . . . 1 volt

##### Maximum Reverse Current:

Static value at maximum-rated peak reverse voltage, forward ma. = 0, free-air temperature of 25° C. . . . . 0.005 ma

Dynamic value at maximum-rated peak reverse voltage, maximum-rated dc forward current, free-air temperature of 65° C. . . . . 0.3 ma

<sup>a</sup> At free-air temperatures up to 65° C. At free-air temperatures above 65° C, see Rating Chart.



# 1N3754

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## OPERATING CONSIDERATIONS

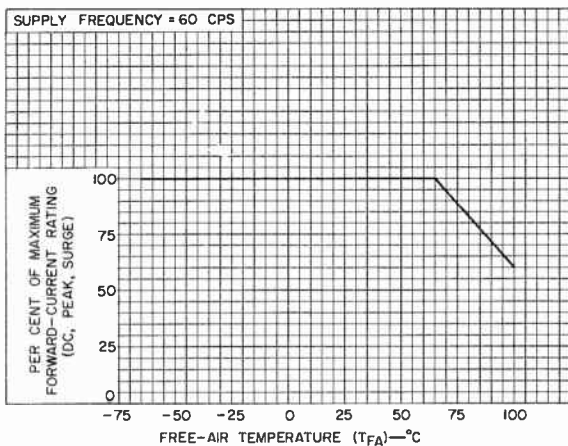
A *surge-limiting impedance* should always be used in series with the rectifier. The impedance value must be sufficient to limit the surge current to the value specified under the maximum ratings. This impedance may be provided by the power-transformer windings, or by an external resistor or choke.

The *flexible leads* of this transistor are usually soldered to the circuit elements. It is desirable in all soldering operations to provide some slack or an expansion elbow in the leads to prevent excessive tension on the leads. It is important during the soldering operation to avoid excessive heat in order to prevent possible damage to the rectifier. To absorb some of the heat, grip the flexible lead of the rectifier between the case and the soldering point with a pair of pliers.

When dip soldering is employed in the assembly of printed circuitry using this rectifier, the leads should not be dip soldered within 0.25" of the metal case.

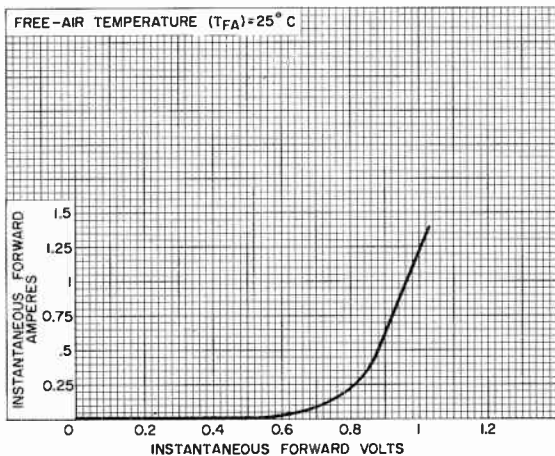


## RATING CHART



92CS-11670R1

## TYPICAL FORWARD CHARACTERISTIC



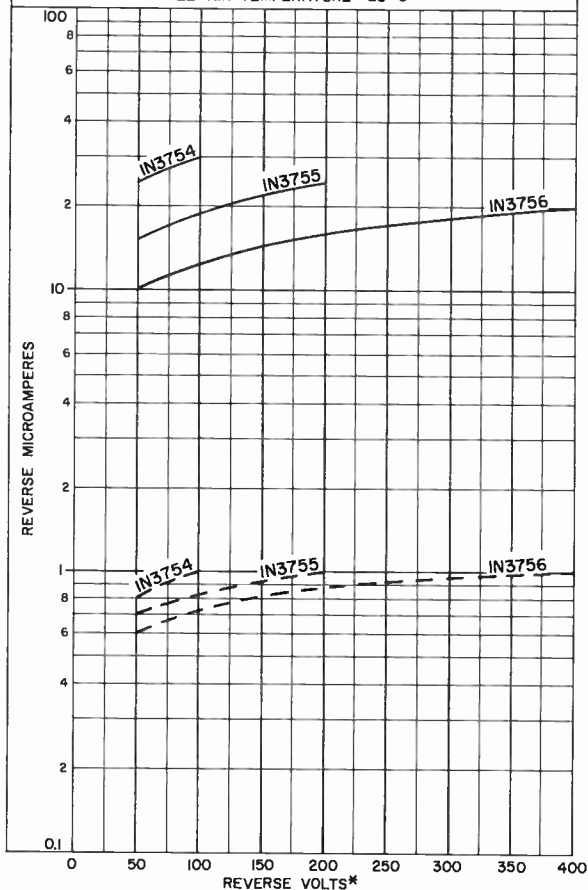
92CS-11669



# IN3754

## TYPICAL REVERSE CHARACTERISTICS

\* DO NOT EXCEED MAXIMUM PEAK-REVERSE-VOLTAGE RATING.  
SOLID-LINE CURVES: DYNAMIC CHARACTERISTICS  
MEASURED AT FREE-AIR TEMPERATURE = 65° C AND AT  
MAXIMUM DC-FORWARD-CURRENT RATING  
BROKEN-LINE CURVES: STATIC CHARACTERISTICS  
MEASURED AT FREE-AIR TEMPERATURE = 25° C



92CM-11671



# 1N3755

## Silicon Rectifier

### DIFFUSED-JUNCTION TYPE

For Industrial and Consumer-Product Applications

The 1N3755 is the same as the 1N3754 except for the following items:

### HALF-WAVE RECTIFIER

Maximum Ratings, *Absolute-Maximum Values:*

*For power-supply frequency of 60  
cps and for capacitor-input filter*

PEAK REVERSE VOLTAGE. . . . .	200 max.	volts
RMS SUPPLY VOLTAGE. . . . .	70 max.	volts





# 1N3756

## Silicon Rectifier

DIFFUSED-JUNCTION TYPE

For Industrial and Consumer-Product Applications

The 1N3756 is the same as the 1N3754 except for the following items:

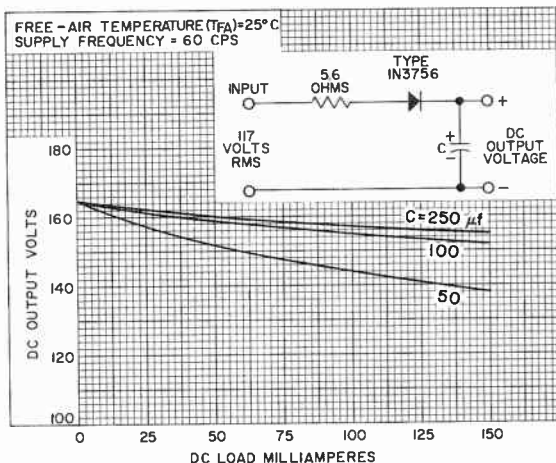
### HALF-WAVE RECTIFIER

Maximum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps  
and for capacitor-input filter

PEAK REVERSE VOLTAGE. . . . . 400 max. volts  
RMS SUPPLY VOLTAGE. . . . . 140 max. volts

### TYPICAL OPERATION CHARACTERISTICS Half-Wave Rectifier

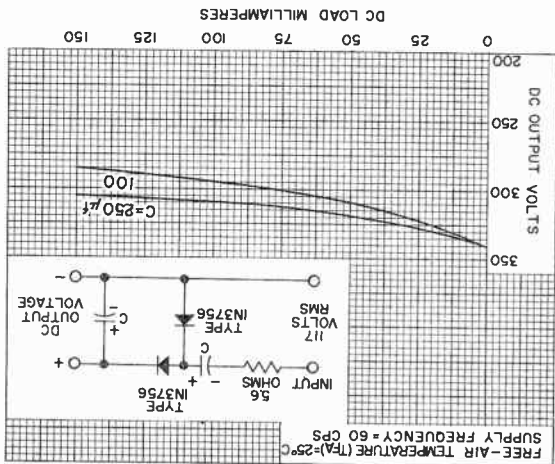


92CS-11672



## TYPICAL OPERATION CHARACTERISTICS

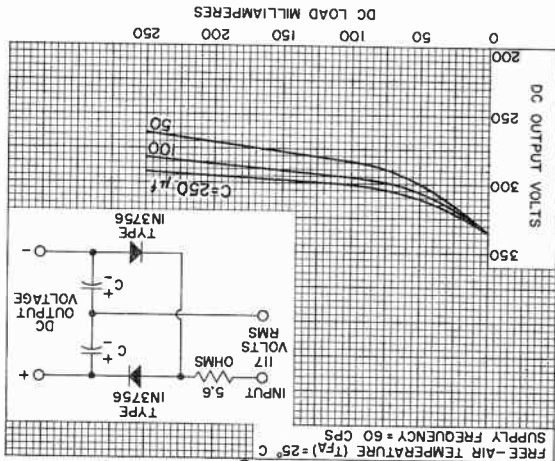
### Half-Wave Voltage Doubler



92CS-11673

## TYPICAL OPERATION CHARACTERISTICS

### Full-Wave Voltage Doubler



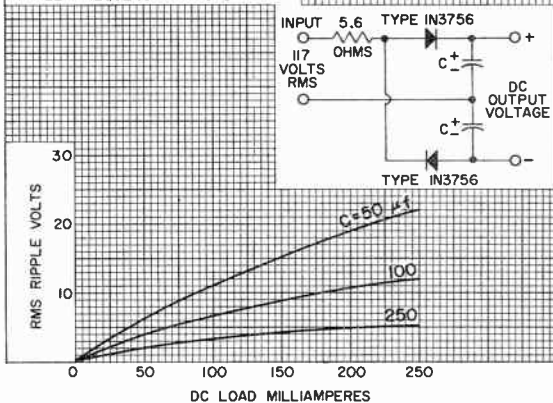
92CS-11674





## TYPICAL OPERATION CHARACTERISTICS Full-Wave Voltage Doubler

FREE-AIR TEMPERATURE ( $T_{FA}$ ) = 25° C  
 SUPPLY FREQUENCY = 60 CPS  
 RIPPLE FREQUENCY = 120 CPS



92CS-11675





# 1N3847

## Tunnel Diode

### GERMANIUM P-ON-N REGION, EPITAXIAL TYPE

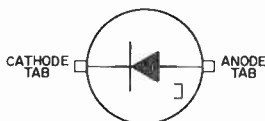
For Switching and Small-Signal Applications Requiring Control ( $\pm 10\%$ ) of Peak-Point Current and Switching Times Greater than 1800 Picoseconds

#### GENERAL DATA

##### Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	0.270"
Maximum Width. . . . .	0.130"
Maximum Height. . . . .	0.055"
Case. . . . .	Metal and Ceramic

Terminal Diagram (See Dimensional Outline):



The arrow indicates direction of forward current flow as indicated by dc ammeter.

#### SWITCHING SERVICE

Maximum and Minimum Ratings, Absolute-Maximum Values:

##### DC CURRENT:

Forward . . . . .	$I_F$	10 max.	ma
Reverse . . . . .	$I_R$	15 max.	ma

##### DISSIPATION:

At free-air temperatures:			
From $-35^\circ$ to $25^\circ$ C. . . . .		5 max.	mw
Above $25^\circ$ C. . . . .	Derate linearly to 0 mw at $100^\circ$ C		

##### FREE-AIR TEMPERATURE RANGE:

Operating . . . . .	$T_{OPR}$	$-35$ to $100$	$^\circ\text{C}$
Storage . . . . .	$T_{STG}$	$-35$ to $100$	$^\circ\text{C}$

##### TAB TEMPERATURE:<sup>a</sup>

For 3 seconds maximum . . . . .	$T_T$	175 max.	$^\circ\text{C}$
---------------------------------	-------	----------	------------------

##### Electrical Characteristics:

At free-air temperature =  $25^\circ$  C

		Min.	Typical	Max.	
Static: <sup>b</sup>					
Peak-Point Current. . . . .	$I_P$	4.5	-	5.5	ma
Valley-Point Current. . . . .	$I_V$	-	-	0.75	ma
Peak-Point-to-Valley-Point Current Ratio . . . . .	$I_P/I_V$	6/1	-	-	
Positive Voltage at peak-point ma. = 5.5 . . . . .	$V_F'$	430	-	590	mv



# 1N3847

Min. Typical Max.

Dynamic:<sup>c</sup>

Terminal Valley-Point

Capacitance <sup>d</sup> . . . . .	C	-	-	25	pf
Total Series Resistance . . .	R <sub>S</sub>	-	-	3	ohms
Switching Time:					
Rise time <sup>e</sup> . . . . .	t <sub>r</sub>	-	1800	-	psec

<sup>a</sup> See Soldering Considerations.

<sup>b</sup> See accompanying Static-Forward-Characteristic graph.

<sup>c</sup> See accompanying Equivalent Circuit of a Tunnel Diode in the Negative-Resistance Region.

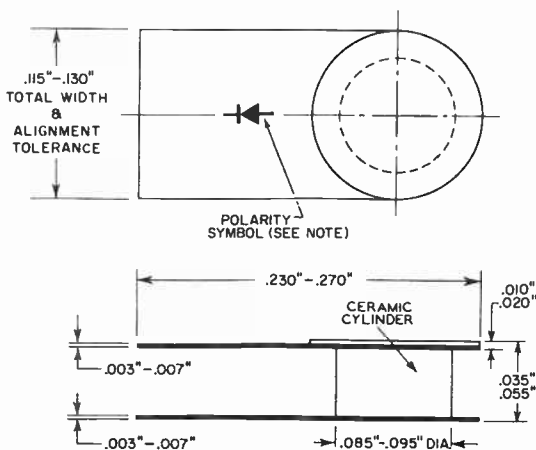
<sup>d</sup> Includes case capacitance of 0.8 pf.

<sup>e</sup> Calculated rise time (approximate) for a germanium tunnel diode when switching from V<sub>p</sub> to V<sub>f</sub> at a constant value of I<sub>p</sub>.

$$t_r \approx \frac{C(V_F - V_P)}{(I_P - I_V)} \approx \frac{C}{2 I_P}$$

## SOLDERING CONSIDERATIONS

A low-temperature solder, (such as Alpha #111 alloy, rosin-filled, or equivalent) should be used. To minimize soldering time, a pre-tinned circuit board should be used. To protect the junction against overheating, the tunnel diode should be held with long-nose pliers.

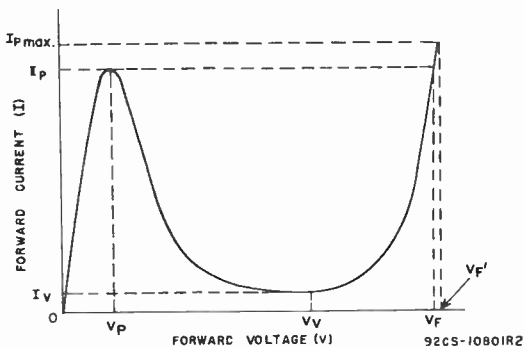


92CS-11806

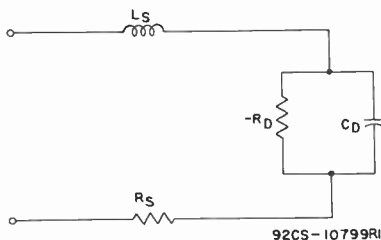
NOTE: ARROW INDICATES DIRECTION OF FORWARD CURRENT FLOW AS INDICATED BY DC AMMETER.



## STATIC FORWARD CHARACTERISTIC OF A TUNNEL DIODE



## EQUIVALENT CIRCUIT OF A TUNNEL DIODE IN THE NEGATIVE-RESISTANCE REGION





## Tunnel Diode

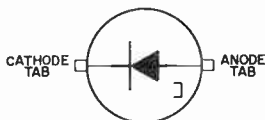
### GERMANIUM P-ON-N REGION, EPITAXIAL TYPE

For Switching and Small-Signal Applications  
Requiring Control ( $\pm 10\%$ ) of Peak-Point Current  
and Switching Times Greater than 900 Picoseconds

#### GENERAL DATA

##### Mechanical:

Operating Position . . . . .	Any
Maximum Overall Length . . . . .	0.270"
Maximum Width . . . . .	0.130"
Maximum Height . . . . .	0.055"
Case . . . . .	Metal and Ceramic
Terminal Diagram (See <i>Dimensional Outline</i> ):	



The arrow indicates direction of forward current flow as indicated by dc ammeter.

#### SWITCHING SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values*:

##### DC CURRENT:

Forward . . . . .	$I_F$	18 max.	ma
Reverse . . . . .	$I_R$	25 max.	ma

##### DISSIPATION:

At free-air temperatures:			
From $-35^{\circ}$ to $25^{\circ}$ C. . . . .		10 max.	mw
Above $25^{\circ}$ C . . . . .		<i>Derate linearly to 0 mw at <math>100^{\circ}</math> C</i>	

##### FREE-AIR TEMPERATURE RANGE:

Operating . . . . .	$T_{OPR}$	$-35$ to $100$	$^{\circ}$ C
Storage . . . . .	$T_{STG}$	$-35$ to $100$	$^{\circ}$ C

##### TAB TEMPERATURE:<sup>a</sup>

For 3 seconds maximum . . . . .	$T_T$	175 max.	$^{\circ}$ C
---------------------------------	-------	----------	--------------

##### Electrical Characteristics:

At free-air temperature =  $25^{\circ}$  C

Min. Typical Max.

##### Static:<sup>b</sup>

Peak-Point Current . . . . .	$I_P$	9	-	11	ma
Valley-Point Current . . . . .	$I_V$	-	-	1.5	ma
Peak-Point-to-Valley-Point Current Ratio . . . . .	$I_P/I_V$	6/1	-	-	
Positive Voltage at peak-point ma. = 11 . . . . .	$V_F'$	440	-	600	mv



# 1N3848

Min. Typical Max.

Dynamic: <sup>c</sup>

Terminal Valley-Point

Capacitance <sup>d</sup> . . . . .	C	-	-	25	pf
Total Series Resistance . . . . .	R <sub>S</sub>	-	-	2.5	ohms
Switching Time:					
Rise time <sup>e</sup> . . . . .	t <sub>r</sub>	-	900	-	psec

<sup>a</sup> See *Soldering Considerations*.

<sup>b</sup> See accompanying *Static-Forward-Characteristic* graph.

<sup>c</sup> See accompanying *Equivalent Circuit of a Tunnel Diode in the Negative-Resistance Region*.

<sup>d</sup> Includes case capacitance of 0.8 pf.

<sup>e</sup> Calculated rise time (approximate) for a germanium tunnel diode when switching from V<sub>p</sub> to V<sub>f</sub> at a constant value of I<sub>p</sub>.

$$t_r \sim \frac{C(V_f - V_p)}{(I_p - I_v)} \sim \frac{C}{2 I_p}$$

SOLDERING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
STATIC FORWARD CHARACTERISTIC  
OF A TUNNEL DIODE,

and

EQUIVALENT CIRCUIT OF A TUNNEL DIODE  
IN THE NEGATIVE-RESISTANCE REGION

shown under Type 1N3847 also apply to the 1N3848





## Tunnel Diode

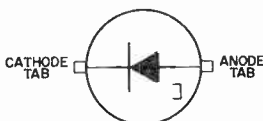
GERMANIUM P-ON-N REGION, EPITAXIAL TYPE

For Switching and Small-Signal Applications  
Requiring Control ( $\pm 10\%$ ) of Peak-Point Current  
and Switching Times Greater than 600 Picoseconds

### GENERAL DATA

#### Mechanical:

Operating Position . . . . .	Any
Maximum Overall Length . . . . .	0.270"
Maximum Width . . . . .	0.130"
Maximum Height . . . . .	0.055"
Case . . . . .	Metal and Ceramic
Terminal Diagram (See <i>Dimensional Outline</i> ):	



The arrow indicates direction of forward current flow as indicated by dc ammeter.

### SWITCHING SERVICE

Maximum and Minimum Ratings, Absolute-Maximum Values:

#### DC CURRENT:

Forward . . . . .	$I_F$	35 max.	ma
Reverse . . . . .	$I_R$	50 max.	ma

#### DISSIPATION:

At free-air temperatures:			
From $-35^\circ$ to $25^\circ$ C . . . . .		20 max.	mw
Above $25^\circ$ C . . . . .	Derate linearly to 0 mw at $100^\circ$ C		

#### FREE-AIR TEMPERATURE RANGE:

Operating . . . . .	$T_{OPR}$	$-35$ to $100$	$^\circ$ C
Storage . . . . .	$T_{STG}$	$-35$ to $100$	$^\circ$ C

#### TAB TEMPERATURE:<sup>a</sup>

For 3 seconds maximum . . . . .	$T_T$	175 max.	$^\circ$ C
---------------------------------	-------	----------	------------

#### Electrical Characteristics:

At free-air temperature =  $25^\circ$  C

Min. Typical Max.

#### Static:<sup>b</sup>

Peak-Point Current . . . . .	$I_P$	18	-	22	ma
Valley-Point Current . . . . .	$I_V$	-	-	3	ma
Peak-Point-to-Valley-Point Current Ratio . . . . .	$I_P/I_V$	6/1	-	-	
Positive Voltage at peak-point ma. = 22 . . . . .	$V_F'$	460	-	620	mv



# 1N3849

Min. Typical Max.

Dynamic:<sup>c</sup>

Terminal Valley-Point

Capacitance <sup>d</sup> . . . . .	C	-	-	30	pf
Total Series Resistance . .	R <sub>S</sub>	-	-	2	ohms
Switching Time:					
Rise time <sup>e</sup> . . . . .	t <sub>r</sub>	-	600	-	psec

<sup>a</sup> See *Soldering Considerations*.

<sup>b</sup> See accompanying *Static-Forward-Characteristic* graph.

<sup>c</sup> See accompanying *Equivalent Circuit of a Tunnel Diode in the Negative-Resistance Region*.

<sup>d</sup> Includes case capacitance of 0.8 pf.

<sup>e</sup> Calculated rise time (approximate) for a germanium tunnel diode when switching from V<sub>p</sub> to V<sub>f</sub> at a constant value of I<sub>p</sub>.

$$t_r \approx \frac{C(V_F - V_P)}{(I_P - I_V)} \approx \frac{C}{2 I_P}$$

SOLDERING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
STATIC FORWARD CHARACTERISTIC  
OF A TUNNEL DIODE,

and

EQUIVALENT CIRCUIT OF A TUNNEL DIODE  
IN THE NEGATIVE-RESISTANCE REGION

shown under Type 1N3847 also apply to the 1N3849



## Tunnel Diode

GERMANIUM P-ON-N REGION, EPITAXIAL TYPE

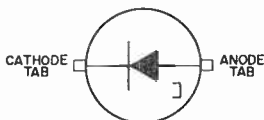
For Switching and Small-Signal Applications  
Requiring Control ( $\pm 10\%$ ) of Peak-Point Current  
and Switching Times Greater than 350 Picoseconds

### GENERAL DATA

#### Mechanical:

Operating Position . . . . .	Any
Maximum Overall Length . . . . .	0.270"
Maximum Width . . . . .	0.130"
Maximum Height . . . . .	0.055"
Case . . . . .	Metal and Ceramic

Terminal Diagram (See *Dimensional Outline*):



The arrow indicates direction of forward current flow as indicated by dc ammeter.

### SWITCHING SERVICE

Maximum and Minimum Ratings, Absolute-Maximum Values:

#### DC CURRENT:

Forward . . . . .	$I_F$	85 max.	ma
Reverse . . . . .	$I_R$	125 max.	ma

#### DISSIPATION:

At free-air temperatures:			
From $-35^\circ$ to $25^\circ$ C . . . . .		50 max.	mw
Above $25^\circ$ C . . . . .	Derate linearly to 0 mw at $100^\circ$ C		

#### FREE-AIR TEMPERATURE RANGE:

Operating . . . . .	$T_{OPR}$	$-35$ to $100$	$^\circ$ C
Storage . . . . .	$T_{STG}$	$-35$ to $100$	$^\circ$ C

#### TAB TEMPERATURE:<sup>a</sup>

For 3 seconds maximum . . . . .	$T_T$	175 max.	$^\circ$ C
---------------------------------	-------	----------	------------

#### Electrical Characteristics:

At free-air temperature =  $25^\circ$  C

Min. Typical Max.

#### Static:<sup>b</sup>

Peak-Point Current . . . . .	$I_P$	45	-	55	ma
Valley-Point Current . . . . .	$I_V$	-	-	7.5	ma
Peak-Point-to-Valley-Point Current Ratio . . . . .	$I_P/I_V$	6/1	-	-	
Positive Voltage at peak-point ma. = 55 . . . . .	$V_F$	530	-	640	mv



# 1N3850

Min. Typical Max.

Dynamic:<sup>c</sup>

Terminal Valley-Point

Capacitance<sup>d</sup> . . . . . C - - 40 pf

Total Series Resistance . . . . . R<sub>S</sub> - - 1.5 ohms

Switching Time:

Rise time<sup>e</sup> . . . . . t<sub>r</sub> - 350 - psec

<sup>a</sup> See Soldering Considerations.

<sup>b</sup> See accompanying Static-Forward-Characteristic graph.

<sup>c</sup> See accompanying Equivalent Circuit of a Tunnel Diode in the Negative-Resistance Region.

<sup>d</sup> Includes case capacitance of 0.8 pf.

<sup>e</sup> Calculated rise time (approximate) for a germanium tunnel diode when switching from V<sub>p</sub> to V<sub>f</sub> at a constant value of I<sub>p</sub>.

$$t_r \approx \frac{C(V_F - V_P)}{(I_P - I_V)} \approx \frac{C}{2 I_P}$$

SOLDERING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
STATIC FORWARD CHARACTERISTIC  
OF A TUNNEL DIODE,

and

EQUIVALENT CIRCUIT OF A TUNNEL DIODE  
IN THE NEGATIVE-RESISTANCE REGION

shown under Type 1N3847 also apply to the 1N3850



## Tunnel Diode

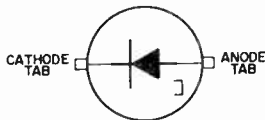
GERMANIUM P-ON-N REGION, EPITAXIAL TYPE

For Switching and Small-Signal Applications Requiring Control ( $\pm 10\%$ ) of Peak-Point Current and Switching Times Greater than 125 Picoseconds

### GENERAL DATA

#### Mechanical:

Operating Position . . . . .	Any
Maximum Overall Length . . . . .	0.270"
Maximum Width . . . . .	0.130"
Maximum Height . . . . .	0.055"
Case . . . . .	Metal and Ceramic
Terminal Diagram (See <i>Dimensional Outline</i> ):	



The arrow indicates direction of forward current flow as indicated by dc ammeter.

### SWITCHING SERVICE

Maximum and Minimum Ratings, Absolute-Maximum Values:

#### DC CURRENT:

Forward . . . . .	$I_F$	170 max.	ma
Reverse . . . . .	$I_R$	250 max.	ma

#### DISSIPATION:

At free-air temperatures:			
From $-35^\circ$ to $25^\circ$ C . . . . .		100 max.	mw
Above $25^\circ$ C . . . . .		<i>Derate linearly to 0 mw at <math>100^\circ</math> C</i>	

#### FREE-AIR TEMPERATURE RANGE:

Operating . . . . .	$T_{OPR}$	$-35$ to $100$	$^\circ$ C
Storage . . . . .	$T_{STG}$	$-35$ to $100$	$^\circ$ C

#### TAB TEMPERATURE:<sup>a</sup>

For 3 seconds maximum . . . . .	$T_T$	175 max.	$^\circ$ C
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#### Electrical Characteristics:

At free-air temperature =  $25^\circ$  C

Min. Typical Max.

#### Static:<sup>b</sup>

Peak-Point Current . . . . .	$I_P$	90	-	110	ma
Valley-Point Current . . . . .	$I_V$	-	-	15	ma
Peak-Point-to-Valley-Point Current Ratio . . . . .	$I_P/I_V$	6/1	-	-	
Positive Voltage at peak-point ma. = 110 . . . . .	$V_F$	540	-	650	mv



# 1N3851

		Min.	Typical	Max.	
Dynamic: <sup>c</sup>					
Terminal Valley-Point					
Capacitance <sup>d</sup> . . . . .	C	-	-	40	pf
Total Series Resistance . .	R <sub>S</sub>	-	-	1	ohm
Switching Time:					
Rise time <sup>e</sup> . . . . .	t <sub>r</sub>	-	125	-	psec

<sup>a</sup> See *Soldering Considerations*.

<sup>b</sup> See accompanying *Static-Forward-Characteristic* graph.

<sup>c</sup> See accompanying *Equivalent Circuit of a Tunnel Diode in the Negative-Resistance Region*.

<sup>d</sup> Includes case capacitance of 0.8 pf.

<sup>e</sup> Calculated rise time (approximate) for a germanium tunnel diode when switching from V<sub>p</sub> to V<sub>f</sub> at a constant value of I<sub>p</sub>.

$$t_r \approx \frac{C(V_F - V_P)}{(I_P - I_V)} \approx \frac{C}{2 I_P}$$

SOLDERING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
STATIC FORWARD CHARACTERISTIC  
OF A TUNNEL DIODE,  
and  
EQUIVALENT CIRCUIT OF A TUNNEL DIODE  
IN THE NEGATIVE-RESISTANCE REGION  
shown under Type 1N3847 also apply to the 1N3851



# 1N3852

## Tunnel Diode

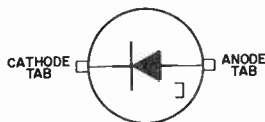
GERMANIUM P-ON-N REGION, EPITAXIAL TYPE

For Switching and Small-Signal Applications Requiring Control ( $\pm 5\%$ ) of Peak-Point Current and Switching Times Greater than 1200 Picoseconds

### GENERAL DATA

#### Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	0.270"
Maximum Width . . . . .	0.130"
Maximum Height. . . . .	0.055"
Case. . . . .	Metal and Ceramic
Terminal Diagram (See <i>Dimensional Outline</i> ):	



The arrow indicates direction of forward current flow as indicated by dc ammeter.

### SWITCHING SERVICE

Maximum and Minimum Ratings, Absolute-Maximum Values:

#### DC CURRENT:

Forward . . . . .	$I_F$	10 max.	ma
Reverse . . . . .	$I_R$	15 max.	ma

#### DISSIPATION:

At free-air temperatures:			
From $-35^\circ$ to $25^\circ$ C. . . . .		5 max.	mw
Above $25^\circ$ C. . . . .	Derate linearly to 0 mw at $100^\circ$ C		

#### FREE-AIR TEMPERATURE RANGE:

Operating . . . . .	$T_{OPR}$	$-35$ to $100$	$^\circ$ C
Storage . . . . .	$T_{STG}$	$-35$ to $100$	$^\circ$ C

#### TAB TEMPERATURE:<sup>a</sup>

For 3 seconds maximum . . . . .	$T_T$	175 max.	$^\circ$ C
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#### Electrical Characteristics:

At free-air temperature =  $25^\circ$  C

Min. Typical Max.

#### Static:<sup>b</sup>

Peak-Point Current. . . . .	$I_P$	4.75	-	5.25	ma
Valley-Point Current. . . . .	$I_V$	-	-	0.6	ma
Peak-Point-to-Valley-Point Current Ratio . . . . .	$I_P/I_V$	8/1	-	-	
Peak-Point Voltage. . . . .	$V_P$	50	-	90	mv
Valley-Point Voltage. . . . .	$V_V$	330	-	-	mv
Positive Voltage at peak-point ma. = 5.25. . . . .	$V_{F'}$	490	-	560	mv



# 1N3852

Min. Typical Max.

Dynamic:<sup>c</sup>

Terminal Valley-Point

Capacitance<sup>d</sup>. . . . . C - - 15 pf

Total Series Resistance . . . R<sub>S</sub> - - 3 ohms

Switching Time:

Rise time<sup>e</sup>. . . . . t<sub>r</sub> - 1200 - psec

<sup>a</sup> See *Soldering Considerations*.

<sup>b</sup> See accompanying *Static-Forward-Characteristic* graph.

<sup>c</sup> See accompanying *Equivalent Circuit of a Tunnel Diode in the Negative-Resistance Region*.

<sup>d</sup> Includes case capacitance of 0.8 pf.

<sup>e</sup> Calculated rise time (approximate) for a germanium tunnel diode when switching from V<sub>p</sub> to V<sub>f</sub> at a constant value of I<sub>p</sub>.

$$t_r \approx \frac{C(V_f - V_p)}{(I_p - I_f)} \approx \frac{C}{2 I_p}$$

SOLDERING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
STATIC FORWARD CHARACTERISTIC  
OF A TUNNEL DIODE,  
and

EQUIVALENT CIRCUIT OF A TUNNEL DIODE  
IN THE NEGATIVE-RESISTANCE REGION

shown under Type 1N3847 also apply to the 1N3852





## Tunnel Diode

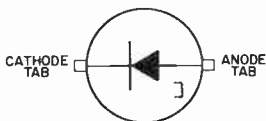
GERMANIUM P-ON-N REGION, EPITAXIAL TYPE

For Switching and Small-Signal Applications  
Requiring Control ( $\pm 5\%$ ) of Peak-Point Current  
and Switching Times Greater than 600 Picoseconds

### GENERAL DATA

#### Mechanical:

Operating Position . . . . .	Any
Maximum Overall Length . . . . .	0.270"
Maximum Width . . . . .	0.130"
Maximum Height . . . . .	0.055"
Case . . . . .	Metal and Ceramic
Terminal Diagram (See <i>Dimensional Outline</i> ):	



The arrow indicates direction of forward current flow as indicated by dc ammeter.

### SWITCHING SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values:*

#### DC CURRENT:

Forward . . . . .	$I_F$	18 max.	ma
Reverse . . . . .	$I_R$	25 max.	ma

#### DISSIPATION:

At free-air temperatures:			
From $-35^\circ$ to $25^\circ$ C . . . . .		10 max.	mw
Above $25^\circ$ C . . . . .	Derate linearly to 0 mw at $100^\circ$ C		

#### FREE-AIR TEMPERATURE RANGE:

Operating . . . . .	$T_{OPR}$	$-35$ to $100$	$^\circ$ C
Storage . . . . .	$T_{STG}$	$-35$ to $100$	$^\circ$ C

#### TAB TEMPERATURE:<sup>a</sup>

For 3 seconds maximum . . . . .	$T_T$	175 max.	$^\circ$ C
---------------------------------	-------	----------	------------

### Electrical Characteristics:

At free-air temperature =  $25^\circ$  C

#### Static:<sup>b</sup>

		Min.	Typical	Max.	
Peak-Point Current . . . . .	$I_P$	9.5	-	10.5	ma
Valley-Point Current . . . . .	$I_V$	-	-	1.2	ma
Peak-Point-to-Valley-Point Current Ratio . . . . .	$I_P/I_V$	8/1	-	-	
Peak-Point Voltage . . . . .	$V_P$	55	-	95	mv
Valley-Point Voltage . . . . .	$V_V$	350	-	-	mv
Positive Voltage at peak-point ma. = 10.5 . . . . .	$V_{F'}$	510	-	580	mv



# 1N3853

Dynamic: <sup>c</sup>	Min.	Typical	Max.	
Terminal Valley-Point Capacitance <sup>d</sup> . . . . . C	-	-	15	pf
Total Series Resistance . . . . R <sub>S</sub>	-	-	2.5	ohms
Switching Time:				
Rise time <sup>e</sup> . . . . . t <sub>r</sub>	-	600	-	psec

<sup>a</sup> See *Soldering Considerations*.

<sup>b</sup> See accompanying *Static-Forward-Characteristic* graph.

<sup>c</sup> See accompanying *Equivalent Circuit of a Tunnel Diode in the Negative-Resistance Region*.

<sup>d</sup> Includes case capacitance of 0.8 pf.

<sup>e</sup> Calculated rise time (approximate) for a germanium tunnel diode when switching from V<sub>p</sub> to V<sub>F</sub> at a constant value of I<sub>p</sub>.

$$t_r \approx \frac{C(V_F - V_P)}{(I_P - I_V)} \approx \frac{C}{2 I_P}$$

**SOLDERING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
STATIC FORWARD CHARACTERISTIC  
OF A TUNNEL DIODE,**

and

**EQUIVALENT CIRCUIT OF A TUNNEL DIODE  
IN THE NEGATIVE-RESISTANCE REGION**

shown under Type 1N3847 also apply to the 1N3853



## Tunnel Diode

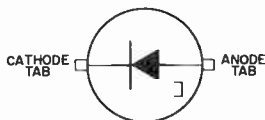
GERMANIUM P-ON-N REGION, EPITAXIAL TYPE

For Switching and Small-Signal Applications  
Requiring Control ( $\pm 5\%$ ) of Peak-Point Current  
and Switching Times Greater than 400 Picoseconds

### GENERAL DATA

#### Mechanical:

Operating Position . . . . . Any  
Maximum Overall Length . . . . . 0.270"  
Maximum Width . . . . . 0.130"  
Maximum Height . . . . . 0.055"  
Case . . . . . Metal and Ceramic  
Terminal Diagram (See *Dimensional Outline*):



The arrow indicates direction of forward current flow as indicated by dc ammeter.

### SWITCHING SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values*:

#### DC CURRENT:

Forward . . . . .	$I_F$	35 max.	ma
Reverse . . . . .	$I_R$	50 max.	ma

#### DISSIPATION:

At free-air temperatures:

From $-35^\circ$ to $25^\circ$ C . . . . .	20 max.	mw
Above $25^\circ$ C . . . . .	<i>Derate linearly to 0 mw at <math>100^\circ</math> C</i>	

#### FREE-AIR TEMPERATURE RANGE:

Operating . . . . .	$T_{OPR}$	$-35$ to $100$	$^\circ\text{C}$
Storage . . . . .	$T_{STG}$	$-35$ to $100$	$^\circ\text{C}$

#### TAB TEMPERATURE:<sup>a</sup>

For 3 seconds maximum . . . . .	$T_T$	175 max.	$^\circ\text{C}$
---------------------------------	-------	----------	------------------

#### Electrical Characteristics:

At free-air temperature =  $25^\circ$  C

#### Static:<sup>b</sup>

		Min.	Typical	Max.	
Peak-Point Current . . . . .	$I_P$	19	-	21	ma
Valley-Point Current . . . . .	$I_V$	-	-	2.4	ma
Peak-Point-to-Valley-Point Current Ratio . . . . .	$I_P/I_V$	8/1	-	-	
Peak-Point Voltage . . . . .	$V_P$	65	-	105	mv
Valley-Point Voltage . . . . .	$V_V$	365	-	-	mv
Positive Voltage at peak-point ma. = 21 . . . . .	$V_{F'}$	530	-	600	mv



# 1N3854

Dynamic: <sup>c</sup>		Min.	Typical	Max.	
Terminal Valley-Point					
Capacitance <sup>d</sup> . . . . .	C	-	-	20	pf
Total Series Resistance . . .	R <sub>S</sub>	-	-	2	ohms
Switching Time:					
Rise time <sup>e</sup> . . . . .	t <sub>r</sub>	-	400	-	psec

<sup>a</sup> See *Soldering Considerations*.

<sup>b</sup> See accompanying *Static-Forward-Characteristic* graph.

<sup>c</sup> See accompanying *Equivalent Circuit of a Tunnel Diode in the Negative-Resistance Region*.

<sup>d</sup> Includes case capacitance of 0.8 pf.

<sup>e</sup> Calculated rise time (approximate) for a germanium tunnel diode when switching from V<sub>p</sub> to V<sub>F</sub> at a constant value of I<sub>p</sub>.

$$t_r \sim \frac{C(V_F - V_P)}{(I_P - I_V)} \sim \frac{C}{2 I_P}$$

SOLDERING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
STATIC FORWARD CHARACTERISTIC  
OF A TUNNEL DIODE,  
and  
EQUIVALENT CIRCUIT OF A TUNNEL DIODE  
IN THE NEGATIVE-RESISTANCE REGION  
shown under Type 1N3847 also apply to the 1N3854



## Tunnel Diode

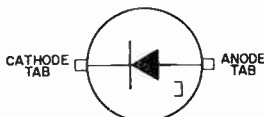
GERMANIUM P-ON-N REGION, EPITAXIAL TYPE

For Switching and Small-Signal Applications  
Requiring Control ( $\pm 5\%$ ) of Peak-Point Current  
and Switching Times Greater than 200 Picoseconds

### GENERAL DATA

#### Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	0.270"
Maximum Width. . . . .	0.130"
Maximum Height. . . . .	0.055"
Case. . . . .	Metal and Ceramic
Terminal Diagram (See <i>Dimensional Outline</i> ):	



The arrow indicates direction of forward current flow as indicated by dc ammeter.

### SWITCHING SERVICE

Maximum and Minimum Ratings, Absolute-Maximum Values:

#### DC CURRENT:

Forward . . . . .	$I_F$	85 max.	ma
Reverse . . . . .	$I_R$	125 max.	ma

#### DISSIPATION:

At free-air temperatures:			
From $-35^\circ$ to $25^\circ$ C. . . . .		50 max.	mw
Above $25^\circ$ C. . . . .	Derate linearly to 0 mw at $100^\circ$ C		

#### FREE-AIR TEMPERATURE RANGE:

Operating . . . . .	$T_{OPR}$	$-35$ to $100$	$^\circ\text{C}$
Storage . . . . .	$T_{STG}$	$-35$ to $100$	$^\circ\text{C}$

#### TAB TEMPERATURE:<sup>a</sup>

For 3 seconds maximum . . . . .	$T_T$	175 max.	$^\circ\text{C}$
---------------------------------	-------	----------	------------------

#### Electrical Characteristics:

At free-air temperature =  $25^\circ$  C

Min. Typical Max.

#### Static:<sup>b</sup>

Peak-Point Current. . . . .	$I_P$	47.5	-	52.5	ma
Valley-Point Current. . . . .	$I_V$	-	-	6	ma
Peak-Point-to-Valley-Point					
Current Ratio . . . . .	$I_P/I_V$	8/1	-	-	
Peak-Point Voltage. . . . .	$V_P$	80	-	130	mv
Valley-Point Voltage. . . . .	$V_V$	380	-	-	mv
Positive Voltage at peak-point					
ma. = 52.5. . . . .	$V_{F'}$	550	-	620	mv



# IN3855

Min. Typical Max.

*Dynamic:*<sup>c</sup>

Terminal Valley-Point Capacitance <sup>d</sup> C	-	-	25	pf
Total Series Resistance . . . . . R <sub>S</sub>	-	-	1.5	ohms
Switching Time:				
Rise time <sup>e</sup> . . . . . t <sub>r</sub>	-	200	-	psec

<sup>a</sup> See *Soldering Considerations*.

<sup>b</sup> See accompanying *Static-Forward-Characteristic* graph.

<sup>c</sup> See accompanying *Equivalent Circuit of a Tunnel Diode in the Negative-Resistance Region*.

<sup>d</sup> Includes case capacitance of 0.8 pf.

<sup>e</sup> Calculated rise time (approximate) for a germanium tunnel diode when switching from V<sub>p</sub> to V<sub>f</sub> at a constant value of I<sub>p</sub>.

$$t_r \sim \frac{C(V_F - V_P)}{(I_P - I_V)} \sim \frac{C}{2 I_P}$$

SOLDERING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
STATIC FORWARD CHARACTERISTIC  
OF A TUNNEL DIODE,

and

EQUIVALENT CIRCUIT OF A TUNNEL DIODE  
IN THE NEGATIVE-RESISTANCE REGION

shown under Type IN3847 also apply to the IN3855



## Tunnel Diode

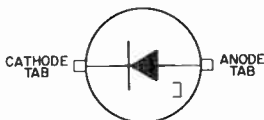
GERMANIUM P-ON-N REGION, EPITAXIAL TYPE

For Switching and Small-Signal Applications  
Requiring Control ( $\pm 5\%$ ) of Peak-Point Current  
and Switching Times Greater than 75 Picoseconds

### GENERAL DATA

#### Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	0.270"
Maximum Width. . . . .	0.130"
Maximum Height. . . . .	0.055"
Case. . . . .	Metal and Ceramic
Terminal Diagram (See <i>Dimensional Outline</i> ):	



The arrow indicates direction of forward current flow as indicated by dc ammeter.

### SWITCHING SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values*:

#### DC CURRENT:

Forward . . . . .	$I_F$	170 max.	ma
Reverse . . . . .	$I_R$	250 max.	ma

#### DISSIPATION:

At free-air temperatures:			
From $-35^{\circ}$ to $25^{\circ}$ C. . . . .		100 max.	mw
Above $25^{\circ}$ C. . . . .	<i>Derate linearly to 0 mw at <math>100^{\circ}</math> C</i>		

#### FREE-AIR TEMPERATURE RANGE:

Operating . . . . .	$T_{OPR}$	$-35$ to $100$	$^{\circ}$ C
Storage . . . . .	$T_{STG}$	$-35$ to $100$	$^{\circ}$ C

#### TAB TEMPERATURE:<sup>a</sup>

For 3 seconds maximum . . . . .	$T_T$	175 max.	$^{\circ}$ C
---------------------------------	-------	----------	--------------

#### Electrical Characteristics:

At free-air temperature =  $25^{\circ}$  C

Min. Typical Max.

#### Static:<sup>b</sup>

Peak-Point Current. . . . .	$I_P$	95	-	105	ma
Valley-Point Current. . . . .	$I_V$	-	-	12	ma
Peak-Point-to-Valley-Point Current Ratio . . . . .	$I_P/I_V$	8/1	-	-	
Peak-Point Voltage. . . . .	$V_P$	90	-	140	mv
Valley-Point Voltage. . . . .	$V_V$	390	-	-	mv
Positive Voltage at peak-point ma. = 105 . . . . .	$V_{F'}$	560	-	630	mv



# 1N3856

Min. Typical Max.

Dynamic:<sup>c</sup>

Terminal Valley-Point

Capacitance<sup>d</sup>. . . . . C - - 25 pf

Total Series Resistance . . . . .  $R_S$  - - 1 ohm

Switching Time:

Rise time<sup>e</sup>. . . . .  $t_r$  - 75 - psec

<sup>a</sup> See *Soldering Considerations*.

<sup>b</sup> See accompanying *Static-Forward-Characteristic* graph.

<sup>c</sup> See accompanying *Equivalent Circuit of a Tunnel Diode in the Negative-Resistance Region*.

<sup>d</sup> Includes case capacitance of 0.8 pf.

<sup>e</sup> Calculated rise time (approximate) for a germanium tunnel diode when switching from  $V_p$  to  $V_f$  at a constant value of  $I_p$ .

$$t_r \approx \frac{C(V_f - V_p)}{(I_p - I_V)} \approx \frac{C}{2 I_p}$$

SOLDERING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
STATIC FORWARD CHARACTERISTIC  
OF A TUNNEL DIODE,

and

EQUIVALENT CIRCUIT OF A TUNNEL DIODE  
IN THE NEGATIVE-RESISTANCE REGION

shown under Type 1N3847 also apply to the 1N3856





## Tunnel Diode

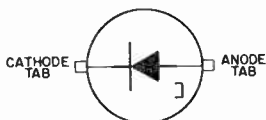
GERMANIUM P-ON-N REGION, EPITAXIAL TYPE

For Switching and Small-Signal Applications  
Requiring Control ( $\pm 5\%$ ) of Peak-Point Current  
and Switching Times Greater than 600 Picoseconds

### GENERAL DATA

#### Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	0.270"
Maximum Width. . . . .	0.130"
Maximum Height. . . . .	0.055"
Case. . . . .	Metal and Ceramic
Terminal Diagram (See <i>Dimensional Outline</i> ):	



The arrow indicates direction of forward current flow as indicated by dc ammeter.

### SWITCHING SERVICE

Maximum and Minimum Ratings, Absolute-Maximum Values:

#### DC CURRENT:

Forward . . . . .	$I_F$	10 max.	ma
Reverse . . . . .	$I_R$	15 max.	ma

#### DISSIPATION:

At free-air temperatures:

From $-35^\circ$ to $25^\circ$ C. . . . .	5 max.	mw
Above $25^\circ$ C. . . . .	Derate linearly to 0 mw at $100^\circ$ C	

#### FREE-AIR TEMPERATURE RANGE:

Operating . . . . .	$T_{OPR}$	$-35$ to $100$	$^\circ$ C
Storage . . . . .	$T_{STG}$	$-35$ to $100$	$^\circ$ C

#### TAB TEMPERATURE:<sup>a</sup>

For 3 seconds maximum . . . . .	$T_T$	175 max.	$^\circ$ C
---------------------------------	-------	----------	------------

#### Electrical Characteristics:

At free-air temperature =  $25^\circ$  C

Min. Typical Max.

#### Static:<sup>b</sup>

Peak-Point Current. . . . .	$I_P$	4.75	-	5.25	ma
Valley-Point Current. . . . .	$I_V$	-	-	0.6	ma
Peak-Point-to-Valley-Point Current Ratio . . . . .	$I_P/I_V$	8/1	-	-	
Peak-Point Voltage. . . . .	$V_P$	50	-	90	mv
Valley-Point Voltage. . . . .	$V_V$	330	-	-	mv
Positive Voltage at peak-point ma. = 5.25. . . . .	$V_{F'}$	490	-	560	mv



# 1N3857

Min. Typical Max.

Dynamic:<sup>c</sup>

Terminal Valley-Point

Capacitance <sup>d</sup> . . . . .	C	-	-	8	pf
Total Series Resistance . .	R <sub>S</sub>	-	-	3	ohms
Switching Time:					
Rise time <sup>e</sup> . . . . .	t <sub>r</sub>	-	600	-	psec

<sup>a</sup> See *Soldering Considerations*.

<sup>b</sup> See accompanying *Static-Forward-Characteristic* graph.

<sup>c</sup> See accompanying *Equivalent Circuit of a Tunnel Diode in the Negative-Resistance Region*.

<sup>d</sup> Includes case capacitance of 0.8 pf.

<sup>e</sup> Calculated rise time (approximate) for a germanium tunnel diode when switching from V<sub>p</sub> to V<sub>f</sub> at a constant value of I<sub>p</sub>.

$$t_r \approx \frac{C(V_F - V_P)}{(I_P - I_V)} \approx \frac{C}{2 I_P}$$

SOLDERING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
STATIC FORWARD CHARACTERISTIC  
OF A TUNNEL DIODE,

and

EQUIVALENT CIRCUIT OF A TUNNEL DIODE  
IN THE NEGATIVE-RESISTANCE REGION

shown under Type 1N3847 also apply to the 1N3857



## Tunnel Diode

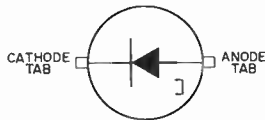
### GERMANIUM P-ON-N REGION, EPITAXIAL TYPE

For Switching and Small-Signal Applications Requiring Control ( $\pm 5\%$ ) of Peak-Point Current and Switching Times Greater than 300 Picoseconds

#### GENERAL DATA

##### Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	0.270"
Maximum Width . . . . .	0.130"
Maximum Height. . . . .	0.055"
Case. . . . .	Metal and Ceramic
Terminal Diagram (See <i>Dimensional Outline</i> );	



The arrow indicates direction of forward current flow as indicated by dc ammeter.

#### SWITCHING SERVICE

Maximum and Minimum Ratings, Absolute-Maximum Values:

##### DC CURRENT:

Forward . . . . .	$I_F$	18 max.	ma
Reverse . . . . .	$I_R$	25 max.	ma
	P		

##### DISSIPATION:

at free-air temperatures:			
From $-35^{\circ}$ to $25^{\circ}$ C. . . . .		10 max.	mw
Above $25^{\circ}$ C . . . . .	Derate linearly to 0 mw at $100^{\circ}$ C		

##### FREE-AIR TEMPERATURE RANGE:

Operating . . . . .	$T_{OPR}$	$-35$ to $100$	$^{\circ}$ C
Storage . . . . .	$T_{STG}$	$-35$ to $100$	$^{\circ}$ C

##### TAB TEMPERATURE:<sup>a</sup>

For 3 seconds maximum . . . . .	$T_T$	175 max.	$^{\circ}$ C
---------------------------------	-------	----------	--------------

##### Electrical Characteristics:

At free-air temperature =  $25^{\circ}$  C

		Min.	Typical	Max.	
Stat.c: <sup>b</sup>					
Peak-Point Current. . . . .	$I_P$	9.5	-	10.5	ma
Valley-Point Current. . . . .	$I_V$	-	-	1.2	ma
Peak-Point-to-Valley-Point Current Ratio . . . . .	$I_P/I_V$	8/1	-	-	
Peak-Point Voltage. . . . .	$V_P$	55	-	95	mv
Valley-Point Voltage. . . . .	$V_V$	350	-	-	mv
Positive Voltage at peak-point ma. = 10.5. . . . .	$V_{F'}$	510	-	580	mv



# 1N3858

Min. Typical Max.

Dynamic:<sup>c</sup>

Terminal Valley-Point

Capacitance <sup>d</sup> . . . . .	C	-	-	8	pf
Total Series Resistance . .	R <sub>S</sub>	-	-	2.5	ohms
Switching Time:					
Rise time <sup>e</sup> . . . . .	t <sub>r</sub>	-	300	-	psec

<sup>a</sup> See *Soldering Considerations*.

<sup>b</sup> See accompanying *Static-Forward-Characteristic* graph.

<sup>c</sup> See accompanying *Equivalent Circuit of a Tunnel Diode in the Negative-Resistance Region*.

<sup>d</sup> Includes case capacitance of 0.8 pf.

<sup>e</sup> Calculated rise time (approximate) for a germanium tunnel diode when switching from V<sub>p</sub> to V<sub>F</sub> at a constant value of I<sub>p</sub>.

$$t_r \approx \frac{C(V_F - V_P)}{(I_P - I_V)} \approx \frac{C}{2 I_P}$$

SOLDERING CONSIDERATIONS,  
 DIMENSIONAL OUTLINE,  
 STATIC FORWARD CHARACTERISTIC  
 OF A TUNNEL DIODE,

and

EQUIVALENT CIRCUIT OF A TUNNEL DIODE  
 IN THE NEGATIVE-RESISTANCE REGION

shown under Type 1N3847 also apply to the 1N3858



## Tunnel Diode

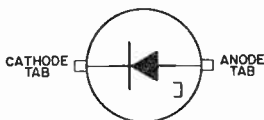
GERMANIUM P-ON-N REGION, EPITAXIAL TYPE

For Switching and Small-Signal Applications Requiring Control ( $\pm 5\%$ ) of Peak-Point Current and Switching Times Greater than 200 Picoseconds

### GENERAL DATA

#### Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	0.270"
Maximum Width. . . . .	0.130"
Maximum Height. . . . .	0.055"
Case. . . . .	Metal and Ceramic
Terminal Diagram (See <i>Dimensional Outline</i> ):	



The arrow indicates direction of forward current flow as indicated by dc ammeter.

### SWITCHING SERVICE

Maximum and Minimum Ratings, Absolute-Maximum Values:

#### DC CURRENT:

Forward . . . . .	$I_F$	35 max.	ma
Reverse . . . . .	$I_R$	50 max.	ma

#### DISSIPATION:

At free-air temperatures:			
From $-35^\circ$ to $25^\circ$ C. . . . .		20 max.	mw
Above $25^\circ$ C. . . . .	Derate linearly to 0 mw at $100^\circ$ C		

#### FREE-AIR TEMPERATURE RANGE:

Operating . . . . .	$T_{OPR}$	$-35$ to $100$	$^\circ$ C
Storage . . . . .	$T_{STG}$	$-35$ to $100$	$^\circ$ C

#### TAB TEMPERATURE:<sup>a</sup>

For 3 seconds maximum . . . . .	$T_T$	175 max.	$^\circ$ C
---------------------------------	-------	----------	------------

#### Electrical Characteristics:

At free-air temperature =  $25^\circ$  C

		Min.	Typical	Max.	
Static: <sup>b</sup>					
Peak-Point Current. . . . .	$I_P$	19	-	21	ma
Valley-Point Current. . . . .	$I_V$	-	-	2.4	ma
Peak-Point-to-Valley-Point Current Ratio . . . . .	$I_P/I_V$	8/1	-	-	
Peak-Point Voltage. . . . .	$V_P$	65	-	105	mv
Valley-Point Voltage. . . . .	$V_V$	365	-	-	mv
Positive Voltage at peak-point ma. = 21. . . . .	$V_{PI}$	530	-	600	mv



# 1N3859

Min. Typical Max.

Dynamic:<sup>c</sup>

Terminal Valley-Point

Capacitance<sup>d</sup>. . . . . C - - 10 pf

Total Series Resistance . . . . . R<sub>S</sub> - - 2 ohms

Switching Time:

Rise time<sup>e</sup>. . . . . t<sub>r</sub> - 200 - psec

<sup>a</sup> See *Soldering Considerations*.

<sup>b</sup> See accompanying *Static-Forward-Characteristic* graph.

<sup>c</sup> See accompanying *Equivalent Circuit of a Tunnel Diode in the Negative-Resistance Region*.

<sup>d</sup> Includes case capacitance of 0.8 pf.

<sup>e</sup> Calculated rise time (approximate) for a germanium tunnel diode when switching from V<sub>p</sub> to V<sub>F</sub> at a constant value of I<sub>p</sub>.

$$t_r \approx \frac{C(V_F - V_P)}{(I_P - I_V)} \approx \frac{C}{2 I_P}$$

SOLDERING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
STATIC FORWARD CHARACTERISTIC  
OF A TUNNEL DIODE,

and

EQUIVALENT CIRCUIT OF A TUNNEL DIODE  
IN THE NEGATIVE-RESISTANCE REGION

shown under Type 1N3847 also apply to the 1N3859



## Tunnel Diode

GERMANIUM P-ON-N REGION, EPITAXIAL TYPE

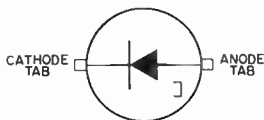
For Switching and Small-Signal Applications  
Requiring Control ( $\pm 5\%$ ) of Peak-Point Current  
and Switching Times Greater than 150 Picoseconds

### GENERAL DATA

#### Mechanical:

Operating Position . . . . .	Any
Maximum Overall Length . . . . .	0.270"
Maximum Width . . . . .	0.130"
Maximum Height . . . . .	0.055"
Case . . . . .	Metal and Ceramic

Terminal Diagram (See Dimensional Outline):



The arrow indicates direction of forward current flow as indicated by dc ammeter.

### SWITCHING SERVICE

Maximum and Minimum Ratings, Absolute-Maximum Values:

#### DC CURRENT:

Forward . . . . .	$I_F$	85 max.	ma
Reverse . . . . .	$I_R$	125 max.	ma

#### DISSIPATION:

At free-air temperatures:			
From $-35^\circ$ to $25^\circ$ C . . . . .		50 max.	mw
Above $25^\circ$ C . . . . .	Derate linearly to 0 mw at $100^\circ$ C		

#### FREE-AIR TEMPERATURE RANGE:

Operating . . . . .	$T_{OPR}$	-35 to 100	$^\circ$ C
Storage . . . . .	$T_{STG}$	-35 to 100	$^\circ$ C

#### TAB TEMPERATURE:<sup>a</sup>

For 3 seconds maximum . . . . .	$T_T$	175 max.	$^\circ$ C
---------------------------------	-------	----------	------------

#### Electrical Characteristics:

At free-air temperature =  $25^\circ$  C

Min. Typical Max.

#### Static:<sup>b</sup>

Peak-Point Current . . . . .	$I_P$	47.5	-	52.5	ma
Valley-Point Current . . . . .	$I_V$	-	-	6	ma
Peak-Point-to-Valley-Point Current Ratio . . . . .	$I_P/I_V$	8/1	-	-	
Peak-Point Voltage . . . . .	$V_P$	80	-	130	mv
Valley-Point Voltage . . . . .	$V_V$	380	-	-	mv
Positive Voltage at peak-point ma. = 52.5 . . . . .	$V_F'$	550	-	620	mv



# 1N3860

Min. Typical Max.

Dynamic:<sup>c</sup>

Terminal Valley-Point Capacitance <sup>d</sup> . C	-	-	12	pf
Total Series Resistance . . . . . R <sub>S</sub>	-	-	1.5	ohms
Switching Time:				
Rise time <sup>e</sup> . . . . . t <sub>r</sub>	-	150	-	psec

<sup>a</sup> See *Soldering Considerations*.

<sup>b</sup> See accompanying *Static-Forward-Characteristic* graph.

<sup>c</sup> See accompanying *Equivalent Circuit of a Tunnel Diode in the Negative-Resistance Region*.

<sup>d</sup> Includes case capacitance of 0.8 pf.

<sup>e</sup> Calculated rise time (approximate) for a germanium tunnel diode when switching from V<sub>p</sub> to V<sub>f</sub> at a constant value of I<sub>p</sub>.

$$t_r \approx \frac{C(V_f - V_p)}{(I_p - I_f)} \approx \frac{C}{2 I_p}$$

SOLDERING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
STATIC FORWARD CHARACTERISTIC  
OF A TUNNEL DIODE,

and

EQUIVALENT CIRCUIT OF A TUNNEL DIODE  
IN THE NEGATIVE-RESISTANCE REGION

shown under Type 1N3847 also apply to the 1N3860





## Tunnel Rectifier

GERMANIUM P-ON-N REGION, EPITAXIAL TYPE

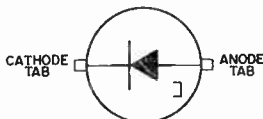
For use as Coupling Device in Memory Systems and other Switching Applications

### GENERAL DATA

#### Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	0.270"
Maximum Width . . . . .	0.130"
Maximum Height. . . . .	0.075"
Case. . . . .	Metal and Ceramic

Terminal Diagram (See Dimensional Outline):



The arrow indicates direction of forward current flow as indicated by dc ammeter.

### SWITCHING SERVICE

Maximum and Minimum Ratings, Absolute-Maximum Values:

DC CURRENT:			
Forward . . . . .	$I_F$	10 max.	ma
Reverse . . . . .	$I_R$	30 max.	ma
DISSIPATION:			
At free-air temperatures:			
From $-35^{\circ}$ to $25^{\circ}$ C. . . . .		10 max.	mw
Above $25^{\circ}$ C . . . . .		Derate linearly to 0 mw at $100^{\circ}$ C	
FREE-AIR TEMPERATURE RANGE:			
Operating . . . . .	$T_{OPR}$	$-35$ to $100$	$^{\circ}$ C
Storage . . . . .	$T_{STG}$	$-35$ to $100$	$^{\circ}$ C
TAB TEMPERATURE: <sup>a</sup>			
For 3 seconds maximum . . . . .	$T_C$	175 max.	$^{\circ}$ C

#### Electrical Characteristics:

At free-air temperature =  $25^{\circ}$  C

		Min.	Max.	
Peak-Point Current. . . . .	$I_P$	0.1	1	ma
Reverse Voltage <sup>b</sup> for dc reverse				
ma. = 10. . . . .	$V_R$	-	170	mv
Positive Voltage at peak-point				
ma. = 1 . . . . .	$V_F$	400	-	mv
Terminal Valley-Point Capacitance <sup>c</sup> . . . . .	C	-	6	pf

<sup>a</sup> See Soldering Considerations.

<sup>b</sup> See accompanying Static Characteristic of Tunnel Rectifier graph.

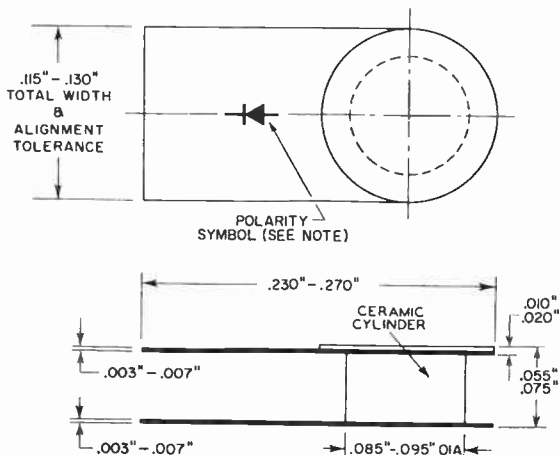
<sup>c</sup> Includes case capacitance of 0.4 pf.



# 1N3861

## SOLDERING CONSIDERATIONS

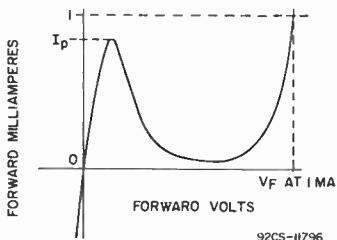
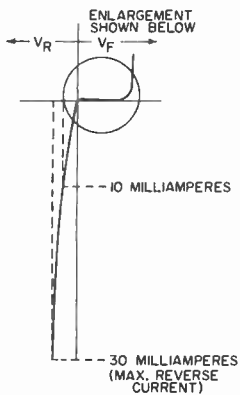
A low-temperature solder, (such as Alpha #111 alloy, rosin-filled, or equivalent) should be used. To minimize soldering time, a pre-tinned circuit board should be used. To protect the junction against overheating, the tunnel rectifier should be held with long-nose pliers.



92CS-11807

NOTE: ARROW INDICATES DIRECTION OF FORWARD CURRENT FLOW AS INDICATED BY DC AMMETER.

## STATIC CHARACTERISTIC OF A TUNNEL RECTIFIER





## Tunnel Rectifier

GERMANIUM P-ON-N REGION, EPITAXIAL TYPE  
 For use as Coupling Device in Memory  
 Systems and other Switching Applications

The 1N3862 is the same as the 1N3861 except for the following items:

### Electrical Characteristics:

At free-air temperature = 25° C

		Min.	Max.	
Reverse Voltage: <sup>b</sup>	$V_R$			
With dc reverse ma. = 10. . . . .		-	150	mv
With dc reverse ma. = 30. . . . .		-	300	mv
Positive Voltage at peak point ma. = 1. . . . .	$V_F$	420	-	mv
Terminal Valley-Point Capacitance <sup>c</sup> . . . . .	C	-	4	pf

<sup>b</sup> See accompanying Static Characteristic of Tunnel Rectifier graph.

<sup>c</sup> Includes case capacitance of 0.4 pf.





## Tunnel Rectifier

GERMANIUM P-ON-N REGION, EPITAXIAL TYPE  
 For use as Coupling Device in Memory  
 Systems and other Switching Applications

The 1N3863 is the same as the 1N3861 except for the following items:

### Electrical Characteristics:

At free-air temperature = 25° C

		Min.	Max.	
Peak-Point Current. . . . .	$I_P$	0.1	0.5	ma
Reverse Voltage: <sup>b</sup>	$V_R$			
With dc reverse ma. = 10. . . . .		-	150	mv
With dc reverse ma. = 30. . . . .		-	300	mv
Positive Voltage at peak point ma. = 1. . . . .	$V_F$	435	-	mv
Terminal Valley-Point Capacitance <sup>c</sup> . . . . .	C	-	4	pf

<sup>b</sup> see accompanying *Static Characteristic of Tunnel Rectifier* graph.  
<sup>c</sup> includes case capacitance of 0.4 pf.







## Silicon Rectifier

## With Integral R-C Voltage-Equalizing Network

## DIFFUSED-JUNCTION TYPE

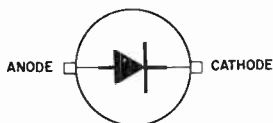
For Industrial and Military Equipment

Designed to Meet Stringent Military Mechanical and Environmental Specifications

## GENERAL DATA

## Mechanical:

Operating Position <sup>a</sup> . . . . .	Any
Dimensions . . . . .	See <i>Dimensional Outline</i>
Case:	
Material . . . . .	Insulating
Material flammability . . . . .	Self-Quenching
Seals . . . . .	Hermetic
Weight (Approx.) . . . . .	2 oz
Terminal Diagram:	



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

## HALF-WAVE RECTIFIER

## Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load, and at altitudes up to 30,000 feet

PEAK REVERSE VOLTAGE (Repetitive) . . . . .	1200 max.	volts	←
PEAK-TRANSIENT REVERSE VOLTAGE (Non-repetitive, for duration of 5-milliseconds maximum):			
At free-air temperature of +60° to +125° C. . . . .	1440 max.	volts	
At other free-air temperatures. . . . .	See <i>Peak-Transient Reverse-Voltage Rating Chart</i>		
RMS SUPPLY VOLTAGE . . . . .	840 max.	volts	
DC BLOCKING VOLTAGE . . . . .	1200 max.	volts	
AVERAGE FORWARD CURRENT:			←
At free-air temperature of 60° C. . . . .	850 max.	ma	
At free-air temperature of 100° C. . . . .	350 max.	ma	
At other free-air temperatures. . . . .	See <i>Average-Forward- Current Rating Chart</i>		
PEAK RECURRENT CURRENT . . . . .	5 max.	amp	

← Indicates a change.



# CR101

## PEAK SURGE CURRENT:<sup>b</sup>

For one-half cycle, sine wave . . . . . 15 max. amp  
For one or more cycles, sine wave . . See *Peak-Surge-Current Rating Chart*

## FREE-AIR TEMPERATURE RANGE:

Operating and storage . . . . . -65 to +125 °C

## Characteristics:

### Maximum Full-Cycle Average Forward

Voltage Drop at maximum-rated operating conditions. . . . . 1.2 volts

Instantaneous Forward Voltage Drop. See *Instantaneous Forward Characteristics Curve*

### Maximum Reverse Current:

Dynamic (Averaged over one complete cycle at maximum ratings)<sup>c</sup>. . . . . 0.3 ma

DC (At maximum rated dc blocking voltage and any temperature within the operating temperature range). . . . . 0.6 ma

### Shunt Capacitance:

Maximum . . . . . 600 pf

Minimum . . . . . 350 pf

<sup>a</sup> See *Operating Considerations*.

<sup>b</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>c</sup> Example: For type CR101 at 60° C free-air temperature, average forward ma. = 850, peak reverse volts = 1200.

## OPERATING CONSIDERATIONS

This high-voltage silicon rectifier can be mounted in any position. It is recommended that wherever possible this rectifier be mounted on a vertical surface to prevent an accumulation of dust on the surface between the rectifier terminals.

A *surge-limiting impedance* should always be used in series with the rectifier. The impedance value must be sufficient to limit the surge current to the value specified under the maximum ratings. This impedance may be provided by the power transformer windings, or by an external resistor or choke.

This rectifier is designed to operate at full ratings at altitudes up to 30,000 feet. For operation at altitudes above 10,000 feet, it is recommended that adequate spacing be provided between rectifiers and between rectifiers and other components (including the chassis and enclosure) to help prevent corona. If the applied voltage exceeds 5500 volts peak, the rectifiers should be mounted on 1-1/2-inch standoff insulators.

When several rectifiers are to be operated in series across a supply voltage of 20,000 volts peak or more, the protection afforded by the integral voltage-equalizing networks may not be adequate, depending on the circuit arrangement and the physical layout of the components. Consequently, additional protection against high transient voltages may be required in the design



of the equipment. For additional information on this subject, write to RCA, Commercial Engineering, Somerville, New Jersey.

Because this rectifier operates at voltages which are dangerous, care should be taken in the design and operation of the equipment to prevent personnel from coming in contact with the rectifier.

Connections to the solder lugs of this rectifier should be made with 16-gauge (or smaller diameter) wire. Care should be exercised during the soldering operation to prevent overheating of the rectifier terminals. A clean, well-tinned iron is recommended to keep soldering time to a minimum.

During a period of prolonged heating, for example, during lead unwrapping, a heat sink such as the jaws of a pair of long-nose pliers should be used between the tip of the soldering iron and the rectifier case.

### MECHANICAL AND ENVIRONMENTAL TESTS

This silicon rectifier is designed to meet the following rigorous mechanical and environmental tests:

#### Shock:

MIL-STD-202B, method 202A

MIL-S-19500B, paragraph 40.10

The device is subjected to 5 blows in each of the orientations ( $X_1$ ,  $Y_1$ , and  $Z_1$ ) with an acceleration of 50 g and a duration of approximately 11 milliseconds.

#### Vibration Fatigue:

MIL-S-19500B, paragraph 40.1B

The device is subjected to a simple harmonic motion at any single frequency between 40 and 100 cycles per second with a constant peak acceleration of 20 g. The vibration shall be applied for 32 hours minimum in each of the orientations  $X_1$ ,  $Y_1$ , and  $Z_1$  (a total of 96 hours minimum).

#### Vibration, Variable Frequency:

MIL-S-19500B, paragraph 40.20

#### Barometric Pressure:

MIL-STD-202B, method 105B, Condition A

(Operation at altitude of 30,000 feet)

MIL-S-19500B, paragraph 40.1

#### Moisture Resistance:

MIL-STD-202B, method 106A

MIL-S-19500B, paragraph 40.6

#### Salt Spray (Corrosion):

MIL-STD-202B, method 101A, Condition A

(Length of test—96 hours)

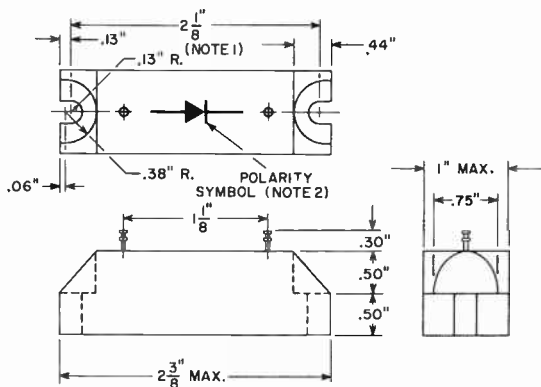
MIL-S-19500B, paragraph 40.9

#### Temperature Cycling:

MIL-STD-202B, method 102A, Condition C

MIL-S-19500B, paragraph 40.14



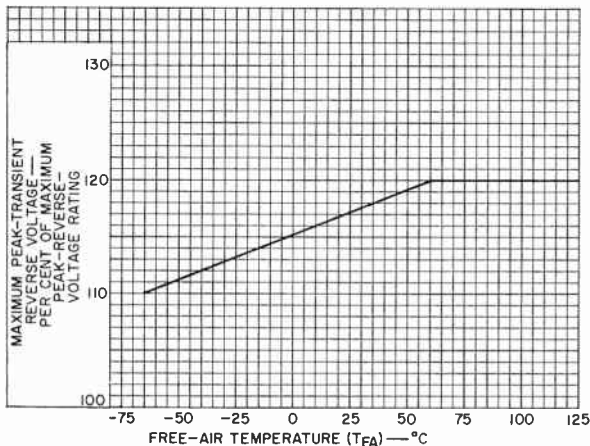


92CS-11251R1

NOTE 1: DISTANCE BETWEEN CENTERS OF MOUNTING HOLES FOR  $\frac{1}{4}$ "-DIAMETER BOLTS.

NOTE 2: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.

## PEAK-TRANSIENT REVERSE-VOLTAGE RATING CHART



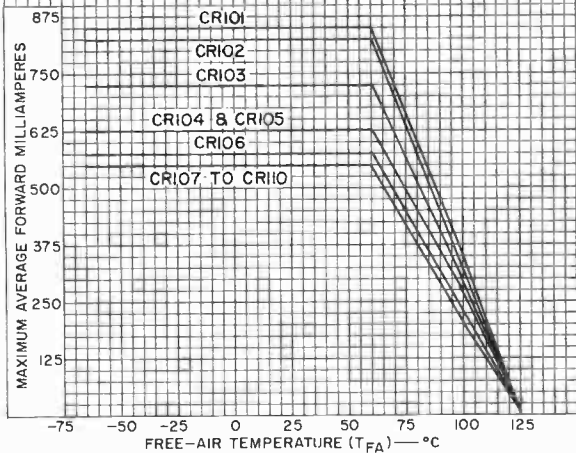
92CS-11701R1

## AVERAGE-FORWARD-CURRENT RATING CHART

FOR DC AND POLYPHASE OPERATION,  
MULTIPLY MAXIMUM-AVERAGE-FORWARD-  
CURRENT RATING FOR EACH RECTIFIER  
BY THE FOLLOWING FACTOR:

TYPE OF OPERATION	FACTOR
DIRECT CURRENT	1.10
THREE PHASE	0.89
SIX PHASE	0.68

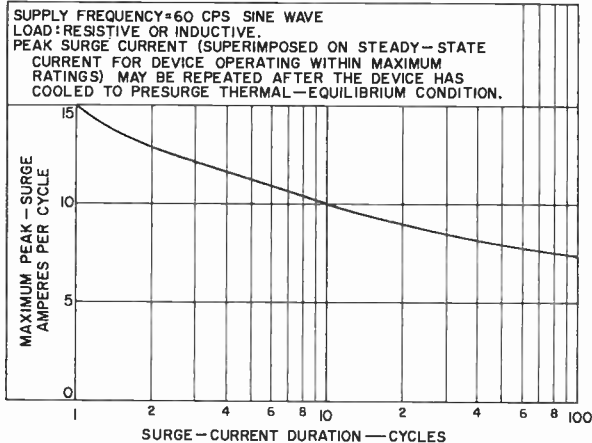
LOAD: RESISTIVE OR INDUCTIVE.



92CM-11794



## PEAK-SURGE-CURRENT RATING CHART



92CS-11123R1



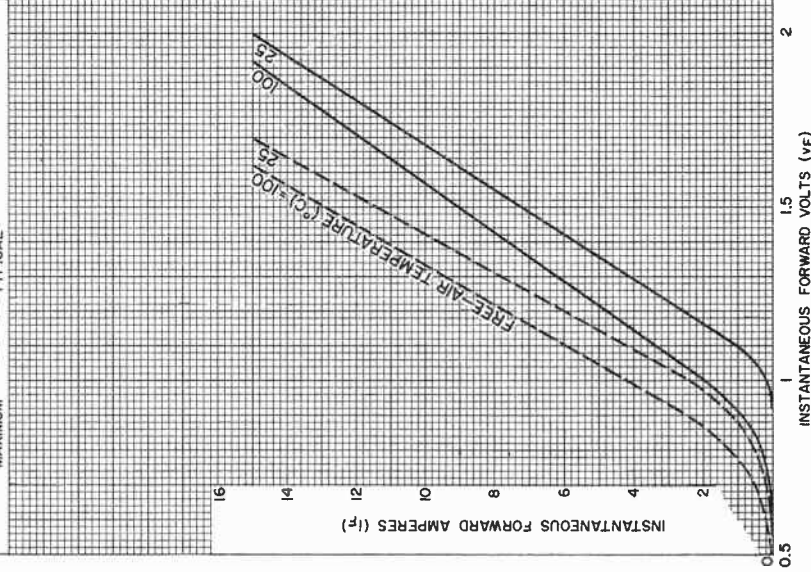
## INSTANTANEOUS FORWARD CHARACTERISTICS Typical and Maximum Values

TO DETERMINE  $v_f$  FOR EACH RECTIFIER TYPE: MULTIPLY  
VALUE GIVEN AT INTERSECTION OF CURVE FOR THE  
APPROPRIATE TEMPERATURE WITH THE DESIRED VALUE  $i_f$   
BY THE FOLLOWING FACTOR:

RCA TYPE	FACTOR	RCA TYPE	FACTOR
CRI01	2	CRI06	10
CRI02	4	CRI07	12
CRI03	5	CRI08	13
CRI04	7	CRI09	15
CRI05	8	CRI10	16

— MAXIMUM

-- TYPICAL







## Silicon Rectifier

### With Integral R-C Voltage-Equalizing Network

#### DIFFUSED-JUNCTION TYPE

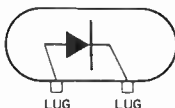
For Industrial and Military Equipment

Designed to Meet Stringent Military Mechanical and Environmental Specifications

#### GENERAL DATA

##### Mechanical:

Operating Position<sup>a</sup> . . . . . Any  
 Dimensions . . . . . See *Dimensional Outline*  
 Case:  
 Material . . . . . Insulating  
 Material flammability . . . . . Self-Quenching  
 Seals . . . . . Hermetic  
 Weight (Approx.) . . . . . 2 oz  
 Terminal Diagram:



The arrow indicates direction of forward (easy) current flow as indicated by 2c ammeter.

#### HALF-WAVE RECTIFIER

Maximum and Minimum Ratings, *Absolute-Maximum Values:*

*For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load, and at altitudes up to 30,000 feet*

PEAK INVERSE VOLTAGE . . . . .	1200 max.	volts
RMS SUPPLY VOLTAGE . . . . .	840 max.	volts
DC BLOCKING VOLTAGE . . . . .	1200 max.	volts
AVERAGE FORWARD CURRENT:		
At ambient temperature of 60° C . . . . .	825 max.	ma
At ambient temperature of 100° C . . . . .	320 max.	ma
At other ambient temperatures . . . . .	See <i>Average-Forward-Current Rating Chart</i>	
PEAK RECURRENT CURRENT . . . . .	5 max.	amp
PEAK SLURGE CURRENT: <sup>b</sup>		
For one-half cycle, sine wave . . . . .	15 max.	amp
For one or more cycles . . . . .	See <i>Peak-Surge-Current Rating Chart</i>	
AMBIENT-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +125	°C



# CR101

## Characteristics:

Maximum Full-Cycle Average Forward Voltage Drop at maximum-rated operating conditions . . . . . 1.2 volts  
Instantaneous Forward Voltage Drop . See *Instantaneous Forward Characteristics Curve*

Maximum Reverse Current:  
Dynamic (averaged over one complete cycle at maximum ratings)<sup>c</sup> . . . . . 0.3 ma  
DC at maximum rated dc blocking voltage and any temperature within the operating temperature range . . . . . 0.6 ma

Shunt Capacitance:  
Maximum . . . . . 600  $\mu\mu\text{f}$   
Minimum . . . . . 350  $\mu\mu\text{f}$

<sup>a</sup> See *Operating Considerations*.

<sup>b</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>c</sup> Example: For type CR101 at 60<sup>o</sup> C ambient temperature, average forward ma. = 825, peak inverse volts = 1200.

## OPERATING CONSIDERATIONS

This high-voltage silicon rectifier can be mounted in any position. It is recommended that wherever possible this rectifier be mounted on a vertical surface to prevent an accumulation of dust on the surface between the rectifier terminals.

A *surge-limiting impedance* should always be used in series with the rectifier. The impedance value must be sufficient to limit the surge current to the value specified under the maximum ratings. This impedance may be provided by the power transformer windings, or by an external resistor or choke.

This rectifier is designed to operate at full ratings at altitudes up to 30,000 feet. For operation at altitudes above 10,000 feet, it is recommended that adequate spacing be provided between rectifiers and between rectifiers and other components (including the chassis and enclosure) to help prevent corona. If the applied voltage exceeds 5500 volts peak, the rectifiers should be mounted on 1-1/2-inch standoff insulators.

When several rectifiers are to be operated in series across a supply voltage of 20,000 volts peak or more, the protection afforded by the integral voltage-equalizing networks may not be adequate, depending on the circuit arrangement and the physical layout of the components. Consequently, additional protection against high transient voltages may be required in the design of the equipment. For additional information on this subject, write to RCA, Commercial Engineering, Somerville, New Jersey.



Because this rectifier operates at voltages which are dangerous, care should be taken in the design and operation of the equipment to prevent personnel from coming in contact with the rectifier.

Connections to the solder lugs of this rectifier should be made with 16-gauge (or smaller diameter) wire. Care should be exercised during the soldering operation to prevent overheating of the rectifier terminals. A clean, well-tinned iron is recommended to keep soldering time to a minimum.

During a period of prolonged heating, for example, during lead unwrapping, a heat sink such as the jaws of a pair of long-nose pliers should be used between the tip of the soldering iron and the rectifier case.

### MECHANICAL AND ENVIRONMENTAL TESTS

This silicon rectifier is designed to meet the following rigorous mechanical and environmental tests:

#### Shock:

MIL-STD-202B, method 202A

MIL-S-19500B, paragraph 40.10

The device is subjected to 5 blows in each of the orientations ( $X_1$ ,  $Y_1$ , and  $Z_1$ ) with an acceleration of 50 g and a duration of approximately 11 milliseconds.

#### Vibration Fatigue:

MIL-S-19500B, paragraph 40.18

The device is subjected to a simple harmonic motion at any single frequency between 40 and 100 cycles per second with a constant peak acceleration of 20 g. The vibration shall be applied for 32 hours minimum in each of the orientations  $X_1$ ,  $Y_1$ , and  $Z_1$  (a total of 96 hours minimum).

#### Vibration, Variable Frequency:

MIL-S-19500B, paragraph 40.20

#### Barometric Pressure:

MIL-STD-202B, method 105B, Condition A  
(Operation at altitude of 30,000 feet)  
MIL-S-19500B, paragraph 40.1

#### Moisture Resistance:

MIL-STD-202B, method 106A  
MIL-S-19500B, paragraph 40.6

#### Salt Spray (Corrosion):

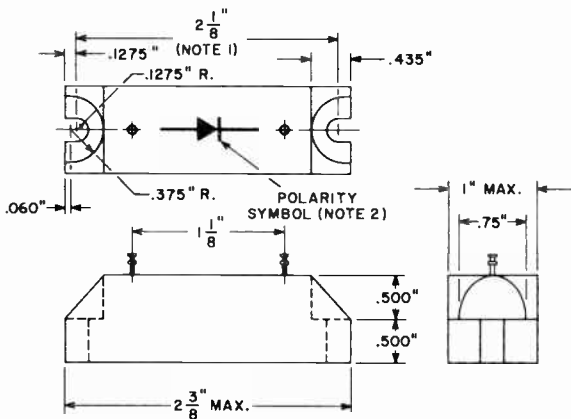
MIL-STD-202B, method 101A, Condition A  
(Length of test—96 hours)  
MIL-S-19500B, paragraph 40.9

#### Temperature Cycling:

MIL-STD-202B, method 102A, Condition C  
MIL-S-19500B, paragraph 40.14



# CR101



92CS-11251

NOTE 1: DISTANCE BETWEEN CENTERS OF MOUNTING HOLES FOR  $1/4$ "-DIAMETER BOLTS.

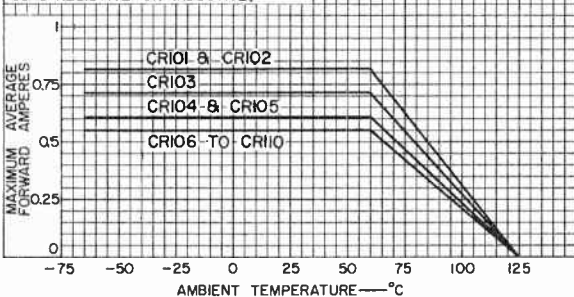
NOTE 2: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC. AMMFTCD

## AVERAGE-FORWARD-CURRENT RATING CHART

FOR DC AND POLYPHASE OPERATION,  
MULTIPLY MAXIMUM FORWARD  
CURRENT RATING FOR EACH RECTIFIER  
BY THE FOLLOWING FACTOR:

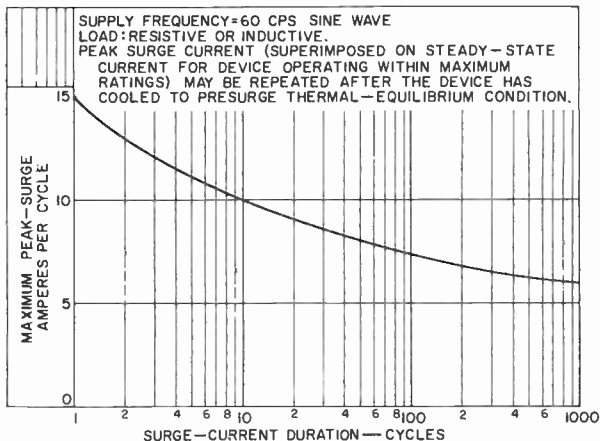
TYPE OF OPERATION	FACTOR
DIRECT CURRENT	1.10
THREE PHASE	0.89
SIX PHASE	0.68

LOAD: RESISTIVE OR INDUCTIVE.



92CS-III24RI

## PEAK-SURGE-CURRENT RATING CHART



92CS-III23



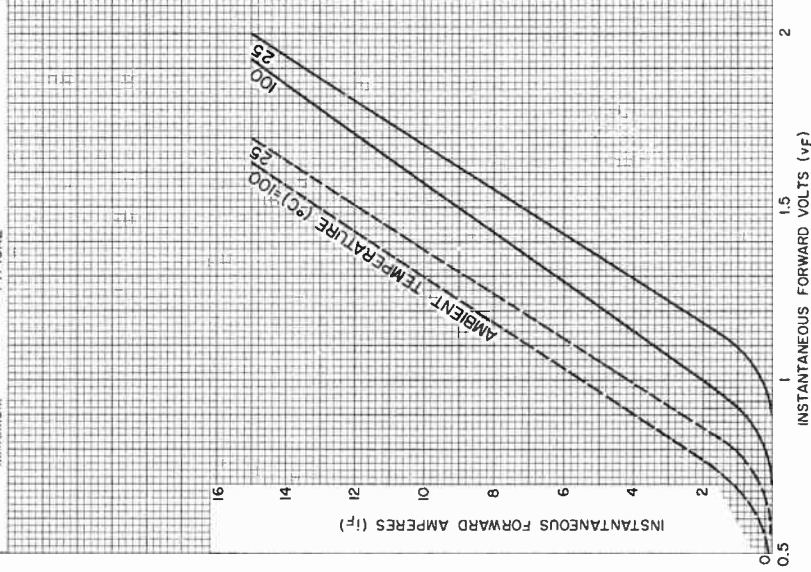
# CR101

## INSTANTANEOUS FORWARD CHARACTERISTICS Typical and Maximum Values

TO DETERMINE  $v_f$  FOR EACH RECTIFIER TYPE: MULTIPLY  
VALUE GIVEN AT INTERSECTION OF CURVE FOR THE  
APPROPRIATE TEMPERATURE WITH THE DESIRED VALUE  $i_f$   
BY THE FOLLOWING FACTOR:

RCA TYPE	FACTOR	RCA TYPE	FACTOR
CR101	2	CR106	10
CR102	4	CR107	12
CR103	5	CR108	13
CR104	7	CR109	15
CR105	8	CR110	16

— MAXIMUM    - - - TYPICAL



92CM-11122

## Silicon Rectifier

### With Integral R-C Voltage-Equalizing Network

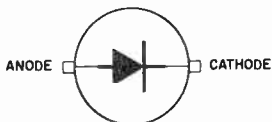
#### DIFFUSED-JUNCTION TYPE

For Industrial and Military Equipment  
 Designed to Meet Stringent Military Mechanical and Environmental Specifications

#### GENERAL DATA

##### Mechanical:

Operating Position<sup>a</sup>. . . . . Any  
 Dimensions . . . . . See *Dimensional Outline*  
 Case:  
 Material . . . . . Insulating  
 Material flammability. . . . . Self-Quenching  
 Seals. . . . . Hermetic  
 Weight (Approx.) . . . . . 2 oz  
 Terminal Diagram: ←



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

#### HALF-WAVE RECTIFIER

##### Maximum and Minimum Ratings, Absolute-Maximum Values:

*For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load, and at altitudes up to 30,000 feet*

PEAK REVERSE VOLTAGE (Repetitive). . . . . 2000 max. volts ←  
 PEAK-TRANSIENT REVERSE VOLTAGE  
 (Non-repetitive, for duration of  
 5-milliseconds maximum):  
 At free-air temperature of +60° to +125°C . . . . . 2400 max. volts  
 At other free-air temperatures . . . . . See *Peak-Transient  
 Reverse-Voltage Rating Chart*  
 RMS SUPPLY VOLTAGE . . . . . 1400 max. volts  
 DC BLOCKING VOLTAGE. . . . . 2000 max. volts  
 AVERAGE FORWARD CURRENT: ←  
 At free-air temperature of 60° C . . . . . 825 max. ma  
 At free-air temperature of 100° C. . . . . 325 max. ma  
 At other free-air temperatures . . . . . See *Average-Forward-  
 Current Rating Chart*  
 PEAK RECURRENT CURRENT . . . . . 5 max. amp

← Indicates a change.



# CR102

## PEAK SURGE CURRENT:<sup>b</sup>

For one-half cycle, sine wave . . . . . 15 max. amp  
For one or more cycles, sine wave . . See *Peak-Surge-Current Rating Chart*

## FREE-AIR TEMPERATURE RANGE:

Operating and storage . . . . . -65 to +125 °C

## Characteristics:

### Maximum Full-Cycle Average Forward Voltage

Drop at maximum rated operating conditions. . . . . 2.4 volts

Instantaneous Forward Voltage Drop. . See *Instantaneous Forward Characteristics Curve*

### Maximum Reverse Current:

Dynamic (Averaged over one complete cycle at maximum ratings)<sup>c</sup>. . . . . 0.3 ma

DC (At maximum rated dc blocking voltage and any temperature within the operating temperature range). . . . . 0.6 ma

### Shunt Capacitance:

Maximum . . . . . 320 pf  
Minimum . . . . . 175 pf

<sup>a</sup> See *Operating Considerations*.

<sup>b</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>c</sup> Example: For type CR102 at 60° C free-air temperature, average forward ma. = 825, peak reverse volts = 2000.

OPERATING CONSIDERATIONS,  
MECHANICAL AND ENVIRONMENTAL TESTS,  
DIMENSIONAL OUTLINE,  
RATING CHARTS,  
and  
CURVES

shown under type CR101 also apply to the CR102





## Silicon Rectifier

## With Integral R-C Voltage-Equalizing Network

## DIFFUSED-JUNCTION TYPE

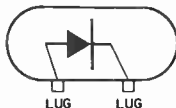
For Industrial and Military Equipment

Designed to Meet Stringent Military Mechanical and Environmental Specifications

## GENERAL DATA

## Mechanical:

Operating Position <sup>a</sup> . . . . .	Any
Dimensions . . . . .	See <i>Dimensional Outline</i>
Case:	
Material . . . . .	Insulating
Material flammability . . . . .	Self-Quenching
Seals . . . . .	Hermetic
Weight (Approx.) . . . . .	2 oz
Terminal Diagram:	



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

## HALF-WAVE RECTIFIER

## Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load, and at altitudes up to 30,000 feet

PEAK INVERSE VOLTAGE . . . . .	2000 max.	volts
RMS SUPPLY VOLTAGE . . . . .	1400 max.	volts
DC BLOCKING VOLTAGE . . . . .	2000 max.	volts
AVERAGE FORWARD CURRENT:		
At ambient temperature of 60° C . . . . .	825 max.	ma
At ambient temperature of 100° C . . . . .	320 max.	ma
At other ambient temperatures . . . . .	See <i>Average-Forward-Current Rating Chart</i>	
PEAK RECURRENT CURRENT . . . . .	5 max.	amp
PEAK SURGE CURRENT: <sup>b</sup>		
For one-half cycle, sine wave . . . . .	15 max.	amp
For one or more cycles . . . . .	See <i>Peak-Surge-Current Rating Chart</i>	
AMBIENT-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +125	°C



# CR102

## Characteristics:

### Maximum Full-Cycle Average Forward Voltage

Drop at maximum rated operating conditions. . . 2.4 volts  
Instantaneous Forward Voltage Drop .See *Instantaneous Forward Characteristics Curve*

### Maximum Reverse Current:

Dynamic (averaged over one complete cycle  
at maximum ratings)<sup>a</sup>. . . . . 0.3 ma  
DC at maximum rated dc blocking voltage  
and any temperature within the operating  
temperature range . . . . . 0.6 ma

### Shunt Capacitance:

Maximum . . . . . 320  $\mu\mu\text{f}$   
Minimum . . . . . 175  $\mu\mu\text{f}$

<sup>a</sup> See *Operating Considerations*.

<sup>b</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>c</sup> Example: For type CR102 at 60° C ambient temperature, average forward ma. = 825, peak inverse volts = 2000.

OPERATING CONSIDERATIONS,  
MECHANICAL AND ENVIRONMENTAL TESTS,  
DIMENSIONAL OUTLINE,  
RATING CHARTS,  
and  
CURVES

Shown under Type CR101 also apply to the CR102



## Silicon Rectifier

### With Integral R-C Voltage-Equalizing Network

#### DIFFUSED-JUNCTION TYPE

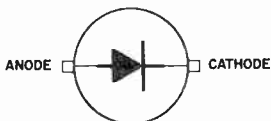
For Industrial and Military Equipment

Designed to Meet Stringent Military Mechanical and Environmental Specifications

#### GENERAL DATA

##### Mechanical:

Operating Position <sup>a</sup> . . . . .	Any
Dimensions. . . . .	See <i>Dimensional Outline</i>
Case:	
Material. . . . .	Insulating
Material flammability . . . . .	Self-Quenching
Seals . . . . .	Hermetic
Weight (Approx.). . . . .	2.1 oz ←
Terminal Diagram:	←



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

#### HALF-WAVE RECTIFIER

##### Maximum and Minimum Ratings, Absolute-Maximum Values:

*For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load, and at altitudes up to 30,000 feet*

PEAK REVERSE VOLTAGE (Repetitive) . . . . .	3000 max. volts	←
PEAK-TRANSIENT REVERSE VOLTAGE (Non-repetitive, for duration of 5-milliseconds maximum):		
At free-air temperatures of +60° to +125° C.	3600 max. volts	
At other free-air temperatures. . . . .	See <i>Peak-Transient Reverse-Voltage Rating Chart</i>	
RMS SUPPLY VOLTAGE. . . . .	2100 max. volts	
DC BLOCKING VOLTAGE . . . . .	3000 max. volts	
AVERAGE FORWARD CURRENT:		←
At free-air temperature of 60° C. . . . .	725 max. ma	
At free-air temperature of 100° C. . . . .	300 max. ma	
At other free-air temperatures. . . . .	See <i>Average-Forward- Current Rating Chart</i>	
PEAK RECURRENT CURRENT. . . . .	5 max. amp	

← Indicates a change.



# CR103

## PEAK SURGE CURRENT:<sup>b</sup>

For one-half cycle, sine wave. . . . . 15 max. amp  
For one or more cycles, sine wave. . See *Peak-Surge-Current  
Rating Chart*

## FREE-AIR TEMPERATURE RANGE:

Operating and storage. . . . . -65 to +125 °C

## Characteristics:

### Maximum Full-Cycle Average Forward Voltage

Drop at maximum rated operating conditions . . . . . 3 volts

Instantaneous Forward Voltage Drop . See *Instantaneous Forward Characteristics Curve*

### Maximum Reverse Current:

Dynamic (Averaged over one complete cycle at maximum ratings)<sup>c</sup> . . . . . 0.3 ma

DC (At maximum rated dc blocking voltage and any temperature within the operating temperature range) . . . . . 0.6 ma

### Shunt Capacitance:

Maximum. . . . . 250 pf

Minimum. . . . . 140 pf

<sup>a</sup> See *Operating Considerations*.

<sup>b</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>c</sup> Example: For type CR103 at 60° C free-air temperature, average forward ma. = 725, peak reverse volts = 3000.

## OPERATING CONSIDERATIONS, MECHANICAL AND ENVIRONMENTAL TESTS, DIMENSIONAL OUTLINE, RATING CHARTS, and CURVES

shown under type CR101 also apply to the CR103



## Silicon Rectifier

## With Integral R-C Voltage-Equalizing Network

## DIFFUSED-JUNCTION TYPE

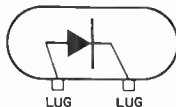
For Industrial and Military Equipment

Designed to Meet Stringent Military Mechanical and Environmental Specifications

## GENERAL DATA

## Mechanical:

Operating Position <sup>a</sup> . . . . .	Any
Dimensions . . . . .	See <i>Dimensional Outline</i>
Case:	
Material . . . . .	Insulating
Material flammability . . . . .	Self-Quenching
Seals . . . . .	Hermetic
Weight (Approx.) . . . . .	2 oz
Terminal Diagram:	



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

## HALF-WAVE RECTIFIER

Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load, and at altitudes up to 30,000 feet

PEAK INVERSE VOLTAGE . . . . .	3000 max.	volts
RMS SUPPLY VOLTAGE . . . . .	2100 max.	volts
DC BLOCKING VOLTAGE . . . . .	3000 max.	volts
AVERAGE FORWARD CURRENT:		
At ambient temperature of 60° C . . . . .	715 max.	ma
At ambient temperature of 100° C . . . . .	275 max.	ma
At other ambient temperatures . . . . .	See <i>Average-Forward-Current Rating Chart</i>	
PEAK RECURRENT CURRENT . . . . .	5 max.	amp
PEAK SURGE CURRENT: <sup>b</sup>		
For one-half cycle, sine wave . . . . .	15 max.	amp
For one or more cycles . . . . .	See <i>Peak-Surge-Current Rating Chart</i>	
AMBIENT-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +125	°C



# CR103

## Characteristics:

Maximum Full-Cycle Average Forward Voltage  
Drop at maximum rated operating conditions. . . . . 3 volts  
Instantaneous Forward Voltage Drop .See *Instantaneous Forward  
Characteristics Curve*

Maximum Reverse Current:  
Dynamic (averaged over one complete  
cycle at maximum ratings)<sup>c</sup>. . . . . 0.3 ma  
DC at maximum rated dc blocking  
voltage and any temperature within  
the operating temperature range . . . . . 0.6 ma

Shunt Capacitance:  
Maximum . . . . . 250  $\mu\mu\text{f}$   
Minimum . . . . . 140  $\mu\mu\text{f}$

<sup>a</sup> See *Operating Considerations*.

<sup>b</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>c</sup> Example: For type CR103 at 60° C ambient temperature, average forward ma. = 715, peak inverse volts = 3000.

**OPERATING CONSIDERATIONS,  
MECHANICAL AND ENVIRONMENTAL TESTS,  
DIMENSIONAL OUTLINE,  
RATING CHARTS,  
and  
CURVES**

Shown under Type CR101 also apply to the CR103



## Silicon Rectifier

## With Integral R-C Voltage-Equalizing Network

## DIFFUSED-JUNCTION TYPE

For Industrial and Military Equipment

Designed to Meet Stringent Military Mechanical and Environmental Specifications

## GENERAL DATA

## Mechanical:

Operating Position<sup>a</sup> . . . . . Any  
 Dimensions. . . . . See *Dimensional Outline*

## Case:

Material. . . . . Insulating  
 Material flammability . . . . . Self-Quenching  
 Seals . . . . . Hermetic

Weight (Approx.). . . . . 3 oz ←  
 Terminal Diagram: ←



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

## HALF-WAVE RECTIFIER

## Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load, and at altitudes up to 30,000 feet

PEAK REVERSE VOLTAGE (Repetitive) . . . . . 4000 max. volts ←

PEAK-TRANSIENT REVERSE VOLTAGE

{Non-repetitive, for duration of 5-milliseconds maximum):

At free-air temperature of

+60° to +125° C. . . . . 4800 max. volts ←

At other free-air temperatures. . . . . See *Peak Transient Reverse Voltage Rating Chart*

RMS SUPPLY VOLTAGE. . . . . 2800 max. volts ←

DC BLOCKING VOLTAGE . . . . . 4000 max. volts ←

## AVERAGE FORWARD CURRENT:

At free-air temperature of 60° C. . . . . 625 max. ma ←

At free-air temperature of 100° C. . . . . 275 max. ma ←

At other free-air temperatures. . . . . See *Average-Forward-Current Rating Chart*

← Indicates a change.



# CR104

PEAK RECURRENT CURRENT. . . . .	5 max.	amp
PEAK SURGE CURRENT: <sup>b</sup>		
For one-half cycle, sine wave . . . . .	15 max.	amp
For one or more cycles, sine wave . . . . .	.See <i>Peak-Surge-Current Rating Chart</i>	

FREE-AIR TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +125	°C

## Characteristics:

Maximum Full-Cycle Average Forward Voltage Drop at maximum rated operating conditions. . . . .	4.2	volts
Instantaneous Forward Voltage Drop. . . . .	.See <i>Instantaneous Forward Characteristics Curve</i>	

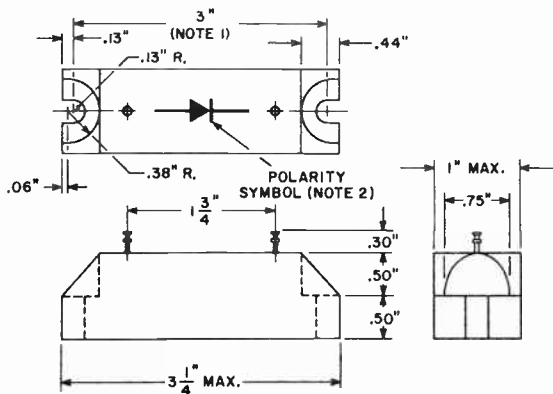
Maximum Reverse Current:		
Dynamic (Averaged over one complete cycle at maximum ratings) <sup>c</sup> . . . . .	0.3	ma
DC (At maximum rated dc blocking voltage and any temperature within the operating temperature range). . . . .	0.6	ma

Shunt Capacitance:		
Maximum . . . . .	175	pf
Minimum . . . . .	100	pf

<sup>a</sup> See *Operating Considerations*.

<sup>b</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>c</sup> Example: For type CR104 at 60°C free-air temperature, average forward ma. = 625, peak reverse volts = 4000.



92CS-11243RI

NOTE 1: DISTANCE BETWEEN CENTERS OF MOUNTING HOLES FOR 1/4"-DIAMETER BOLTS.

NOTE 2: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.





OPERATING CONSIDERATIONS,  
MECHANICAL AND ENVIRONMENTAL TESTS,  
RATING CHARTS,  
and  
CURVES

shown under type CR101 also apply to the CR104





## Silicon Rectifier

## With Integral R-C Voltage-Equalizing Network

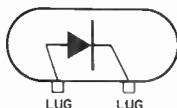
## DIFFUSED-JUNCTION TYPE

For Industrial and Military Equipment  
Designed to Meet Stringent Military Mechanical and Environmental Specifications

## GENERAL DATA

## Mechanical:

Operating Position<sup>a</sup> . . . . . Any  
Dimensions . . . . . See *Dimensional Outline*  
Case:  
Material . . . . . Insulating  
Material flammability . . . . . Self-Quenching  
Seals . . . . . Hermetic  
Weight (Approx.) . . . . . 2.9 oz  
Terminal Diagram:



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

## HALF-WAVE RECTIFIER

## Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load, and at altitudes up to 30,000 feet

PEAK INVERSE VOLTAGE . . . . .	4000 max.	volts
RMS SUPPLY VOLTAGE . . . . .	2800 max.	volts
DC BLOCKING VOLTAGE . . . . .	4000 max.	volts
AVERAGE FORWARD CURRENT:		
At ambient temperature of 60° C . . . . .	605 max.	ma
At ambient temperature of 100° C . . . . .	235 max.	ma
At other ambient temperatures . . . . .	. See <i>Average-Forward-Current Rating Chart</i>	
PEAK RECURRENT CURRENT . . . . .	5 max.	amp
PEAK SURGE CURRENT: <sup>b</sup>		
For one-half cycle, sine wave . . . . .	15 max.	amp
For one or more cycles . . . . .	. See <i>Peak-Surge-Current Rating Chart</i>	
AMBIENT-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +125	°C



# CR104

## Characteristics:

Maximum Full-Cycle Average Forward Voltage

Drop at maximum rated operating conditions. . . 4.2 volts

Instantaneous Forward Voltage Drop .See *Instantaneous Forward Characteristics Curve*

Maximum Reverse Current:

Dynamic (averaged over one complete cycle at maximum ratings)<sup>c</sup>. . . . . 0.3 ma

DC at maximum rated dc blocking voltage and any temperature within the operating temperature range . . . . . 0.6 ma

Shunt Capacitance:

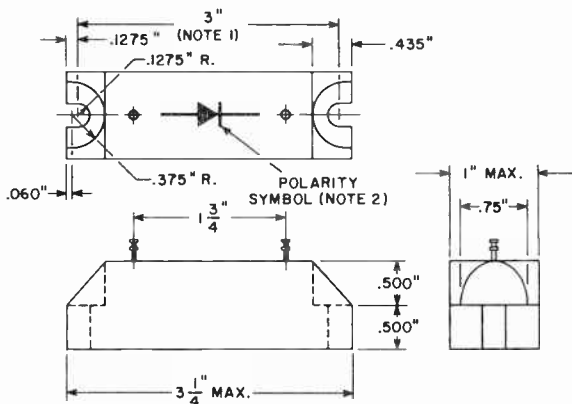
Maximum . . . . . 175  $\mu\mu\text{f}$

Minimum . . . . . 100  $\mu\mu\text{f}$

<sup>a</sup> See *Operating Considerations*.

<sup>b</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>c</sup> Example: For type CR104 at 60° C ambient temperature, average forward ma. = 605, peak inverse volts = 4000.



92CS-11243

NOTE 1: DISTANCE BETWEEN CENTERS OF MOUNTING HOLES FOR 1/4" DIAMETER BOLTS.

NOTE 2: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.

OPERATING CONSIDERATIONS,  
MECHANICAL AND ENVIRONMENTAL TESTS,  
RATING CHARTS,  
and  
CURVES

Shown under Type CR101 also apply to type CR104



## Silicon Rectifier

## With Integral R-C Voltage-Equalizing Network

## DIFFUSED-JUNCTION TYPE

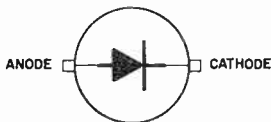
For Industrial and Military Equipment

Designed to Meet Stringent Military Mechanical and Environmental Specifications

## GENERAL DATA

## Mechanical:

Operating Position <sup>a</sup> . . . . .	Any
Dimensions . . . . .	See <i>Dimensional Outline Case</i> :
Material . . . . .	Insulating
Material flammability . . . . .	Self-Quenching
Seals . . . . .	Hermetic
Weight (Approx.) . . . . .	3.1 oz ←
Terminal Diagram:	←



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

## HALF-WAVE RECTIFIER

## Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load, and at altitudes up to 30,000 feet

PEAK REVERSE VOLTAGE (Repetitive) . . . . .	5000 max.	volts
PEAK-TRANSIENT REVERSE VOLTAGE (Non-repetitive, for duration of 5-milliseconds maximum):		←
At free-air temperature of +60° to +125° C. . . . .	6000 max.	volts
At other free-air temperatures. . . . .	See <i>Peak Transient Reverse Voltage Rating Chart</i>	
RMS SUPPLY VOLTAGE . . . . .	3500 max.	volts
DC BLOCKING VOLTAGE . . . . .	5000 max.	volts
AVERAGE FORWARD CURRENT:		←
At free-air temperature of 60° C. . . . .	625 max.	ma
At free-air temperature of 100° C. . . . .	275 max.	ma
At other free-air temperatures. . . . .	See <i>Average-Forward- Current Rating Chart</i>	

← Indicates a change.



# CR105

PEAK RECURRENT CURRENT . . . . .	5 max.	amp
PEAK SURGE CURRENT: <sup>b</sup>		
For one-half cycle, sine-wave . . . . .	15 max.	amp
For one or more cycles, sine wave . . . . .	.See <i>Peak-Surge-Current Rating Chart</i>	
FREE-AIR TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +125	°C

## Characteristics:

Maximum Full-Cycle Average Forward Voltage Drop at maximum rated operating conditions . . . . .	4.8	volts
Instantaneous Forward Voltage Drop. . . . .	.See <i>Instantaneous Forward Characteristics Curve</i>	

## Maximum Reverse Current:

Dynamic (Averaged over one complete cycle at maximum ratings) <sup>c</sup> . . . . .	0.3	ma
DC (At maximum rated dc blocking voltage and any temperature within the operating temperature range) . . . . .	0.6	ma

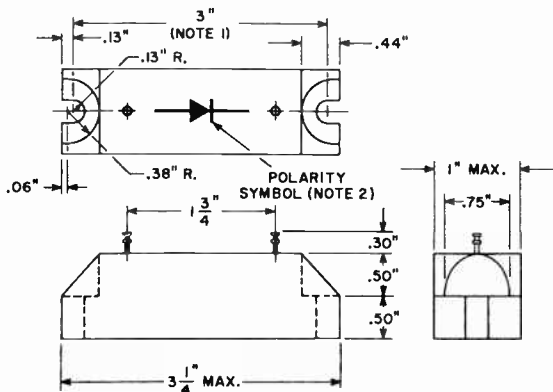
## Shunt Capacitance:

Maximum . . . . .	160	pf
Minimum . . . . .	85	pf

<sup>a</sup> See *Operating Considerations*.

<sup>b</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>c</sup> Example: For type CR105 at 60° C free-air temperature, average forward ma. = 625, peak reverse volts = 5000.



92CS-11243RI

NOTE 1: DISTANCE BETWEEN CENTERS OF MOUNTING HOLES FOR 1/4"-DIAMETER BOLTS.

NOTE 2: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.



OPERATING CONSIDERATIONS,  
MECHANICAL AND ENVIRONMENTAL TESTS,  
RATING CHARTS,  
and  
CURVES

shown under type CR101 also apply to the CR105







## Silicon Rectifier

### With Integral R-C Voltage-Equalizing Network

#### DIFFUSED-JUNCTION TYPE

For Industrial and Military Equipment

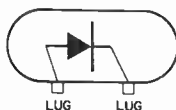
Designed to Meet Stringent Military Mechanical and Environmental Specifications

#### GENERAL DATA

##### Mechanical:

Operating Position <sup>a</sup> . . . . .	Any
Dimensions . . . . .	See <i>Dimensional Outline Case</i>
Material . . . . .	Insulating
Material flammability . . . . .	Self-Quenching
Seals . . . . .	Hermetic
Weight (Approx.) . . . . .	2.9 oz

Terminal Diagram:



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

#### HALF-WAVE RECTIFIER

Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load, and at altitudes up to 30,000 feet

PEAK INVERSE VOLTAGE . . . . .	5000 max.	volts
RMS SUPPLY VOLTAGE . . . . .	3500 max.	volts
DC BLOCKING VOLTAGE . . . . .	5000 max.	volts
AVERAGE FORWARD CURRENT:		
At ambient temperature of 60° C . . . . .	605 max.	ma
At ambient temperature of 100° C . . . . .	235 max.	ma
At other ambient temperatures . . . . .	See <i>Average-Forward-Current Rating Chart</i>	
PEAK RECURRENT CURRENT . . . . .	5 max.	amp
PEAK SURGE CURRENT: <sup>b</sup>		
For one-half cycle, sine-wave . . . . .	15 max.	amp
For one or more cycles . . . . .	See <i>Peak-Surge-Current Rating Chart</i>	
AMBIENT-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +125	°C



# CR105

## Characteristics:

### Maximum Full-Cycle Average Forward Voltage

Drop at maximum rated operating conditions. . . . . 4.8 volts

Instantaneous Forward Voltage Drop .See *Instantaneous Forward Characteristics Curve*

### Maximum Reverse Current:

Dynamic (averaged over one complete cycle at maximum ratings)<sup>c</sup>. . . . . 0.3 ma

DC at maximum rated dc blocking voltage and any temperature within the operating temperature range . . . . . 0.6 ma

### Shunt Capacitance:

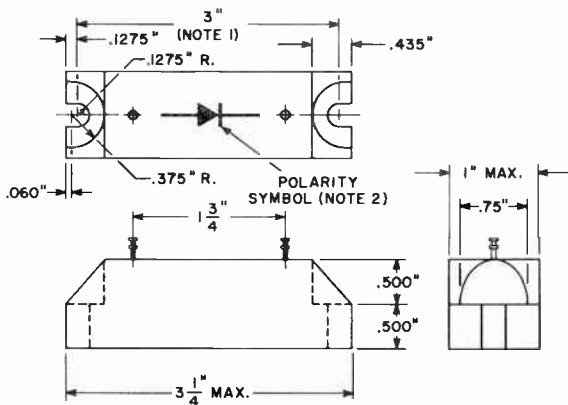
Maximum . . . . . 160  $\mu\text{f}$

Minimum . . . . . 85  $\mu\text{f}$

<sup>a</sup> See *Operating Considerations*.

<sup>b</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>c</sup> Example: For type CR105 at 60° C ambient temperature, average forward  $\text{ma}$  = 605, peak inverse volts = 5000.



92CS-11243

NOTE 1: DISTANCE BETWEEN CENTERS OF MOUNTING HOLES FOR 1/4"-DIAMETER BOLTS.

NOTE 2: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.

OPERATING CONSIDERATIONS,  
MECHANICAL AND ENVIRONMENTAL TESTS,  
RATING CHARTS,  
and  
CURVES

Shown under Type CR101 also apply to the CR105

RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division  
Somerville, N. J.

World Radio History



## Silicon Rectifier

## With Integral R-C Voltage-Equalizing Network

## DIFFUSED-JUNCTION TYPE

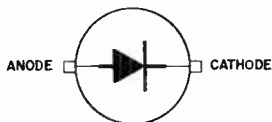
For Industrial and Military Equipment

Designed to Meet Stringent Military Mechanical and Environmental Specifications

## GENERAL DATA

## Mechanical:

Operating Position <sup>a</sup> . . . . .	Any
Dimensions . . . . .	See <i>Dimensional Outline</i>
Case:	
Material . . . . .	Insulating
Material flammability . . . . .	Self-Quenching
Seals . . . . .	Hermetic
Weight (Approx.) . . . . .	4.2 oz
Terminal Diagram:	



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

## HALF-WAVE RECTIFIER

Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load, and at altitudes up to 30,000 feet.

PEAK REVERSE VOLTAGE (Repetitive) . . . . .	6000 max.	volts
PEAK-TRANSIENT REVERSE VOLTAGE (Non-repetitive, for duration of 5-millisecons maximum):		
At free-air temperature of +60° to +125° C . . . . .	4200 max.	volts
At other free-air temperatures . . . . .	See <i>Peak Transient Reverse Voltage Rating Chart</i>	
RMS SUPPLY VOLTAGE . . . . .	4200 max.	volts
DC BLOCKING VOLTAGE . . . . .	6000 max.	volts
AVERAGE FORWARD CURRENT:		
At free-air temperature of 60° C . . . . .	575 max.	ma
At free-air temperature of 100° C . . . . .	225 max.	ma
At other free-air temperatures . . . . .	See <i>Average-Forward- Current Rating Chart</i>	
PEAK RECURRENT CURRENT . . . . .	5 max.	amp

← indicates a change.



# CR106

## PEAK SURGE CURRENT:<sup>b</sup>

For one-half cycle, sine wave . . . . . 15 max. amp  
 For one or more cycles, sine wave . . See *Peak-Surge-Current Rating Chart*

## FREE-AIR TEMPERATURE RANGE:

Operating and Storage . . . . . -65 to +125 °C

## Characteristics:

### Maximum Full-Cycle Average Forward Voltage

Drop at maximum rated operating conditions. . . 6 volts

Instantaneous Forward Voltage Drop. . See *Instantaneous Forward Characteristics Curve*

### Maximum Reverse Current:

Dynamic (Averaged over one complete cycle at maximum ratings)<sup>c</sup>. . . . . 0.3 ma

DC (At maximum rated dc blocking voltage and any temperature within the operating temperature range). . . . . 0.6 ma

### Shunt Capacitance:

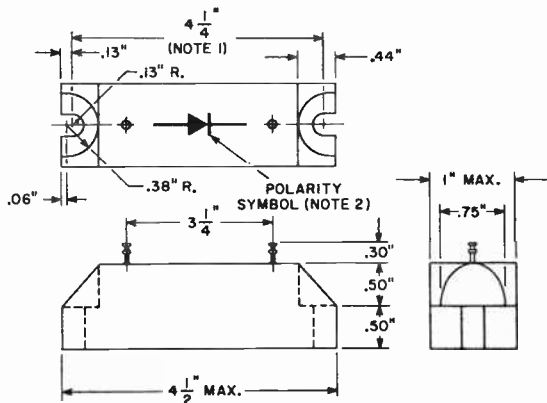
Maximum . . . . . 125 pf

Minimum . . . . . 70 pf

<sup>a</sup> See *Operating Considerations*.

<sup>b</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>c</sup> Example: For type CR106 at 60° C free-air temperature, average forward ma. = 575, peak reverse volts = 6000.



92CS-II249RI

**NOTE 1:** DISTANCE BETWEEN CENTERS OF MOUNTING HOLES FOR 1/4"-DIAMETER BOLTS.

**NOTE 2:** ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.



OPERATING CONSIDERATIONS,  
MECHANICAL AND ENVIRONMENTAL TESTS,  
RATING CHARTS,  
and  
CURVES

shown under type CR101 also apply to the CR106





## Silicon Rectifier

## With Integral R-C Voltage-Equalizing Network

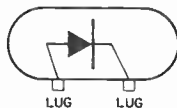
## DIFFUSED-JUNCTION TYPE

For Industrial and Military Equipment  
Designed to Meet Stringent Military Mechanical and Environmental Specifications

## GENERAL DATA

## Mechanical:

Operating Position <sup>a</sup> . . . . .	Any
Dimensions . . . . .	See <i>Dimensional Outline</i>
Case:	
Material . . . . .	Insulating
Material flammability . . . . .	Self-Quenching
Seals . . . . .	Hermetic
Weight (Approx.) . . . . .	4.2 oz
Terminal Diagram:	



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

## HALF-WAVE RECTIFIER

## Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load, and at altitudes up to 30,000 feet.

PEAK INVERSE VOLTAGE . . . . .	6000 max.	volts
RMS SUPPLY VOLTAGE . . . . .	4200 max.	volts
DC BLOCKING VOLTAGE . . . . .	6000 max.	volts
AVERAGE FORWARD CURRENT:		
At ambient temperature of 60° C . . . . .	550 max.	ma
At ambient temperature of 100° C . . . . .	210 max.	ma
At other ambient temperatures . . . . .	See <i>Average-Forward-Current Rating Chart</i>	
PEAK RECURRENT CURRENT . . . . .	5 max.	amp
PEAK SURGE CURRENT: <sup>b</sup>		
For one-half cycle, sine wave . . . . .	15 max.	amp
For one or more cycles. See <i>Peak-Surge-Current Rating Chart</i>		
AMBIENT-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +125	°C



# CR106

## Characteristics:

Maximum Full-Cycle Average Forward Voltage

Drop at maximum rated operating conditions. . . . . 6 volts  
 Instantaneous Forward Voltage Drop .See *Instantaneous Forward Characteristics Curve*

Maximum Reverse Current:

Dynamic (averaged over one complete cycle at maximum ratings)<sup>c</sup>. . . . . 0.3 ma  
 DC at maximum rated dc blocking voltage and any temperature within the operating temperature range . . . . . 0.6 ma

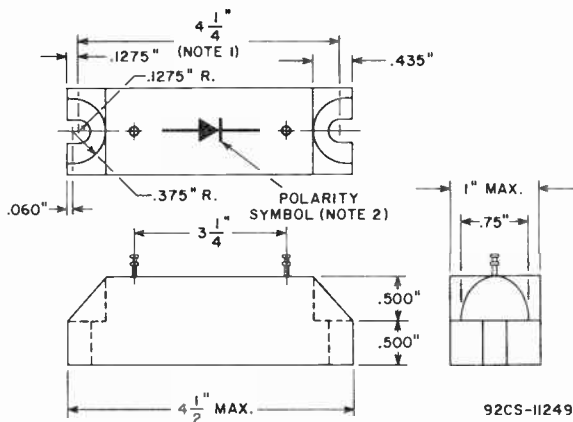
Shunt Capacitance:

Maximum . . . . . 125  $\mu$ f  
 Minimum . . . . . 70  $\mu$ f

<sup>a</sup> See *Operating Considerations*.

<sup>b</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>c</sup> Example: For type CR106 at 60° C ambient temperature, average forward ma. = 550, peak inverse volts = 6000.



NOTE 1: DISTANCE BETWEEN CENTERS OF MOUNTING HOLES FOR  $1/4$ "-DIAMETER BOLTS.

NOTE 2: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.

OPERATING CONSIDERATIONS,  
 MECHANICAL AND ENVIRONMENTAL TESTS,  
 RATING CHARTS,  
 and  
 CURVES

Shown under Type CR101 also apply to the CR106





## Silicon Rectifier

## With Integral R-C Voltage-Equalizing Network

## DIFFUSED-JUNCTION TYPE

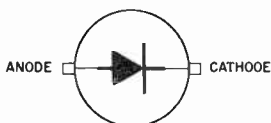
For Industrial and Military Equipment

Designed to Meet Stringent Military Mechanical and Environmental Specifications

## GENERAL DATA

## Mechanical:

Operating Position <sup>a</sup> . . . . .	Any
Dimensions . . . . .	See <i>Dimensional Outline</i>
Case:	
Material . . . . .	Insulating
Material flammability . . . . .	Self-Quenching
Seals . . . . .	Hermetic
Weight (Approx.) . . . . .	4.4 oz ←
Terminal Diagram:	←



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

## HALF-WAVE RECTIFIER

Maximum and Minimum Ratings, *Absolute-Maximum Values:*

For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load, and at altitudes up to 30,000 feet

PEAK REVERSE VOLTAGE (Repetitive) . . . . .	7000 max.	volts ←
PEAK-TRANSIENT REVERSE VOLTAGE (Non-repetitive, for duration of 5-milliseconds maximum):		
At free-air temperature of +60° to +125° C. . . . .	8400 max.	volts
At other free-air temperatures. . . . .	See <i>Peak Transient Reverse Voltage Rating Chart</i>	
RMS SUPPLY VOLTAGE . . . . .	4900 max.	volts
DC BLOCKING VOLTAGE . . . . .	7000 max.	volts
AVERAGE FORWARD CURRENT:		
At free-air temperature of 60° C. . . . .	550 max.	ma
At free-air temperature of 100° C. . . . .	210 max.	ma
At other free-air temperatures. . . . .	See <i>Average-Forward- Current Rating Chart</i>	

← Indicates a change.



# CR107

PEAK RECURRENT CURRENT . . . . .	5 max.	amp
PEAK SURGE CURRENT: <sup>b</sup>		
For one-half cycle, sine wave . . . . .	15 max.	amp
For one or more cycles, sine wave . . . . .	.See <i>Peak-Surge-Current Rating Chart</i>	
FREE-AIR TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +125	°C

## Characteristics:

Maximum Full-Cycle Average Forward Voltage Drop at maximum rated operating conditions . . . . .	7.2	volts
Instantaneous Forward Voltage Drop. . . . .	.See <i>Instantaneous Forward Characteristics Curve</i>	

## Maximum Reverse Current:

Dynamic (Averaged over one complete cycle at maximum ratings) <sup>c</sup> . . . . .	0.3	ma
DC (At maximum rated dc blocking voltage and any temperature within the operating temperature range) . . . . .	0.6	ma

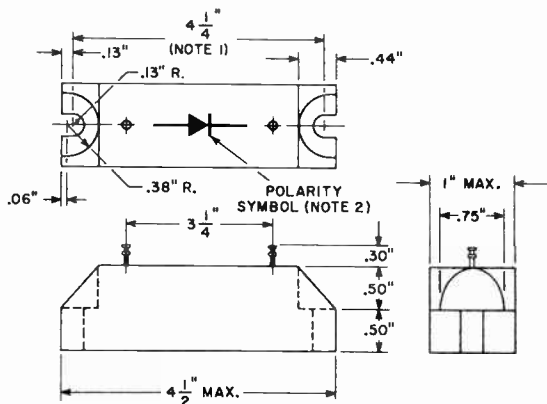
## Shunt Capacitance:

Maximum . . . . .	105	pf
Minimum . . . . .	60	pf

<sup>a</sup> See *Operating Considerations*.

<sup>b</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>c</sup> Example: For type CR107 at 60°C free-air temperature, average forward ma. = 550, peak reverse volts = 7000.



92CS-11249RI

NOTE 1: DISTANCE BETWEEN CENTERS OF MOUNTING HOLES FOR  $1/4$ "-DIAMETER BOLTS.

NOTE 2: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.



OPERATING CONSIDERATIONS,  
MECHANICAL AND ENVIRONMENTAL TESTS,  
RATING CHARTS,  
and  
CURVES

shown under type CR101 also apply to the CR107





## Silicon Rectifier

## With Integral R-C Voltage-Equalizing Network

## DIFFUSED-JUNCTION TYPE

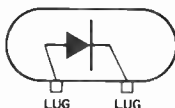
For Industrial and Military Equipment

Designed to Meet Stringent Military Mechanical and Environmental Specifications

## GENERAL DATA

## Mechanical:

Operating Position <sup>a</sup> . . . . .	Any
Dimensions . . . . .	See <i>Dimensional Outline</i>
Case:	
Material . . . . .	Insulating
Material flammability . . . . .	Self-Quenching
Seals . . . . .	Hermetic
Weight (Approx.) . . . . .	4.2 oz
Terminal Diagram:	



*The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.*

## HALF-WAVE RECTIFIER

## Maximum and Minimum Ratings, Absolute-Maximum Values:

*For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load, and at altitudes up to 30,000 feet.*

PEAK INVERSE VOLTAGE . . . . .	7000 max.	volts
RMS SUPPLY VOLTAGE . . . . .	4900 max.	volts
DC BLOCKING VOLTAGE . . . . .	7000 max.	volts
AVERAGE FORWARD CURRENT:		
At ambient temperature of 60° C . . . . .	550 max.	ma
At ambient temperature of 100° C . . . . .	210 max.	ma
At other ambient temperatures . . . . .	See <i>Average-Forward-Current Rating Chart</i>	
PEAK RECURRENT CURRENT . . . . .	5 max.	amp
PEAK SURGE CURRENT: <sup>b</sup>		
For one-half cycle, sine wave . . . . .	15 max.	amp
For one or more cycles. See <i>Peak-Surge-Current Rating Chart</i>		
AMBIENT-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +125	°C



# CR107

## Characteristics:

Maximum Full-Cycle Average Forward Voltage

Drop at maximum rated operating conditions. . . 7.2 volts

Instantaneous Forward Voltage Drop .See *Instantaneous Forward Characteristics Curve*

Maximum Reverse Current:

Dynamic (averaged over one complete cycle at maximum ratings)<sup>c</sup>. . . . . 0.3 ma

DC at maximum rated dc blocking voltage and any temperature within the operating temperature range . . . . . 0.6 ma

Shunt Capacitance:

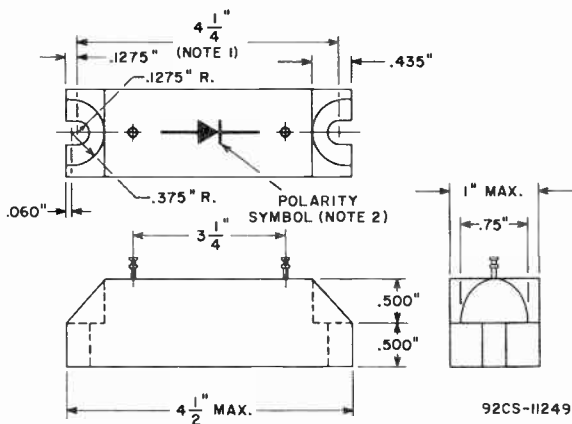
Maximum . . . . . 105  $\mu\text{f}$

Minimum . . . . . 60  $\mu\text{f}$

<sup>a</sup> See *Operating Considerations*.

<sup>b</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>c</sup> Example: For type CR107 at 60° C ambient temperature, average forward ma. = 550, peak inverse volts = 7000.



NOTE 1: DISTANCE BETWEEN CENTERS OF MOUNTING HOLES FOR  $1/4$ "-DIAMETER BOLTS.

NOTE 2: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.

OPERATING CONSIDERATIONS,  
MECHANICAL AND ENVIRONMENTAL TESTS,  
RATING CHARTS,  
and  
CURVES

Shown under Type CR101 also apply to the CR107



## Silicon Rectifier

### With Integral R-C Voltage-Equalizing Network

#### DIFFUSED-JUNCTION TYPE

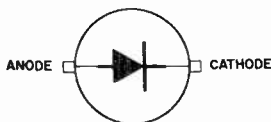
For Industrial and Military Equipment

Designed to Meet Stringent Military Mechanical and Environmental Specifications

#### GENERAL DATA

##### Mechanical:

Operating Position <sup>a</sup> . . . . .	Any
Dimensions . . . . .	See <i>Dimensional Outline</i>
Case:	
Material . . . . .	Insulating
Material flammability . . . . .	Self-Quenching
Seals . . . . .	Hermetic
Weight (Approx.) . . . . .	4.5 oz ←
Terminal Diagram:	←



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

#### HALF-WAVE RECTIFIER

##### Maximum and Minimum Ratings, Absolute-Maximum Values:

*For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load, and at altitudes up to 30,000 feet*

PEAK REVERSE VOLTAGE (Repetitive) . . . . .	8000 max.	volts ←
PEAK-TRANSIENT REVERSE VOLTAGE (Non-repetitive, for duration of 5-milliseconds maximum):		
At free-air temperature of +60° to +125° C. . . . .	9600 max.	volts
At other free-air temperatures . . . . .	See <i>Peak Transient Reverse Voltage Rating Chart</i>	
RMS SUPPLY VOLTAGE . . . . .	5600 max.	volts
DC BLOCKING VOLTAGE . . . . .	8000 max.	volts
AVERAGE FORWARD CURRENT:		
At ambient temperature of 60° C. . . . .	550 max.	ma
At ambient temperature of 100° C. . . . .	210 max.	ma
At other ambient temperatures . . . . .	See <i>Average-Forward- Current Rating Chart</i>	
PEAK RECURRENT CURRENT . . . . .	5 max.	amp

← Indicates a change.



# CR108

## PEAK SURGE CURRENT:<sup>b</sup>

For one-half cycle, sine wave . . . . . 15 max. amp  
 For one or more cycles, sine wave . . See *Peak-Surge-Current Rating Chart*

## FREE-AIR TEMPERATURE RANGE:

Operating and storage . . . . . -65 to +125 °C

## Characteristics:

### Maximum Full-Cycle Average Forward Voltage

Drop at maximum rated operating conditions. . . 7.8 volts  
 Instantaneous Forward Voltage Drop. See *Instantaneous Forward Characteristics Curve*

### Maximum Reverse Current:

Dynamic (Averaged over one complete cycle at maximum ratings)<sup>c</sup>. . . . . 0.3 ma  
 DC (At maximum rated dc blocking voltage and any temperature within the operating temperature range). . . . . 0.6 ma

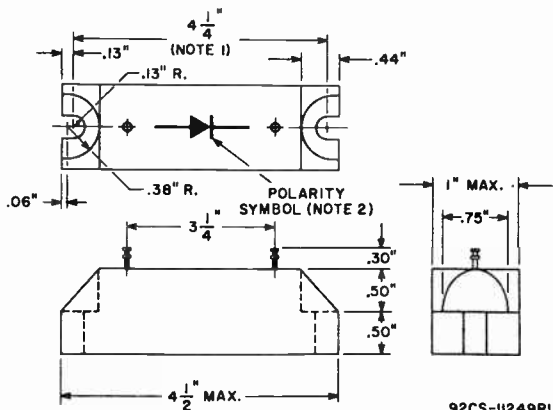
### Shunt Capacitance:

Maximum . . . . . 100 pf  
 Minimum . . . . . 55 pf

<sup>a</sup> See *Operating Considerations*.

<sup>b</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>c</sup> Example: For type CR108 at 60° C free-air temperature, average forward ma. = 550, peak reverse volts = 8000.



92CS-11249R1

NOTE 1: DISTANCE BETWEEN CENTERS OF MOUNTING HOLES FOR 1/4"-DIAMETER BOLTS.

NOTE 2: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.





OPERATING CONSIDERATIONS,  
MECHANICAL AND ENVIRONMENTAL TESTS,  
RATING CHARTS,  
and  
CURVES

shown under type CR101 also apply to the CR108





## Silicon Rectifier

## With Integral R-C Voltage-Equalizing Network

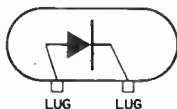
## DIFFUSED-JUNCTION TYPE

For Industrial and Military Equipment  
 Designed to Meet Stringent Military Mechanical and Environmental Specifications

## GENERAL DATA

## Mechanical:

Operating Position<sup>a</sup>. . . . . Any  
 Dimensions . . . . . See *Dimensional Outline Case*:  
 Material . . . . . Insulating  
 Material flammability. . . . . Self-Quenching  
 Seals. . . . . Hermetic  
 Weight (Approx.) . . . . . 4.2 oz  
 Terminal Diagram:



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

## HALF-WAVE RECTIFIER

## Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load, and at altitudes up to 30,000 feet

PEAK INVERSE VOLTAGE. . . . . 8000 max. volts  
 RMS SUPPLY VOLTAGE. . . . . 5600 max. volts  
 DC BLOCKING VOLTAGE . . . . . 8000 max. volts

## AVERAGE FORWARD CURRENT:

At ambient temperature of 60° C . . . . . 550 max. ma  
 At ambient temperature of 100° C. . . . . 210 max. ma  
 At other ambient temperatures . See *Average-Forward-Current Rating Chart*

PEAK RECURRENT CURRENT. . . . . 5 max. amp  
 PEAK SURGE CURRENT:<sup>b</sup>

For one-half cycle, sine wave . . . . . 15 max. amp  
 For one or more cycles. . See *Peak-Surge-Current Rating Chart*

## AMBIENT-TEMPERATURE RANGE:

Operating and storage . . . . . -65 to +125 °C



# CR108

## Characteristics:

### Maximum Full-Cycle Average Forward Voltage

Drop at maximum rated operating conditions. . . . 7.8 volts  
 Instantaneous Forward Voltage Drop .See *Instantaneous Forward Characteristics Curve*

### Maximum Reverse Current:

Dynamic (averaged over one complete cycle at maximum ratings)<sup>a</sup> . . . . . 0.3 ma  
 DC at maximum rated dc blocking voltage and any temperature within the operating temperature range. . . . . 0.6 ma

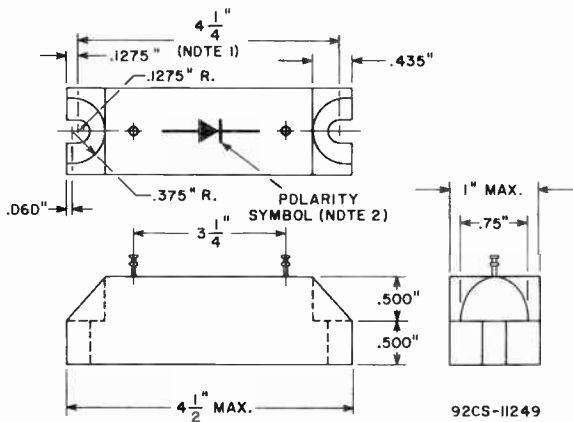
### Shunt Capacitance:

Maximum. . . . . 100  $\mu$ f  
 Minimum. . . . . 55  $\mu$ f

<sup>a</sup> See *Operating Considerations*.

<sup>b</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>c</sup> Example: For type CR108 at 60° C ambient temperature, average forward ma. = 550, peak inverse volts = 8000.



NOTE 1: DISTANCE BETWEEN CENTERS OF MOUNTING HOLES FOR 1/4"-DIAMETER BOLTS.

NOTE 2: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.

OPERATING CONSIDERATIONS,  
 MECHANICAL AND ENVIRONMENTAL TESTS,  
 RATING CHARTS,  
 and  
 CURVES

Shown under Type CR101 also apply to the CR108



## Silicon Rectifier

### With Integral R-C Voltage-Equalizing Network

#### DIFFUSED-JUNCTION TYPE

For Industrial and Military Equipment  
 Designed to Meet Stringent Military Mechanical and Environmental Specifications

#### GENERAL DATA

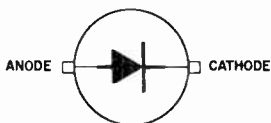
##### Mechanical:

Operating Position<sup>a</sup> . . . . . Any  
 Dimensions . . . . . See *Dimensional Outline*

##### Case:

Material . . . . . Insulating  
 Material flammability . . . . . Self-Quenching  
 Seals . . . . . Hermetic  
 Weight (Approx.) . . . . . 5.4 oz ←

Terminal Diagram: ←



*The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.*

#### HALF-WAVE RECTIFIER

##### Maximum and Minimum Ratings, Absolute-Maximum Values:

*For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load, and at altitudes up to 30,000 feet*

PEAK REVERSE VOLTAGE (Repetitive) . . . . . 9000 max. volts ←

PEAK-TRANSIENT REVERSE VOLTAGE  
 (Non-repetitive, for duration of  
 5-milliseconds maximum):

At free-air temperature of  
 +60° to +125° C. . . . . 10800 max. volts

At other free-air temperatures. . . . . See *Peak Transient  
 Reverse Voltage Rating Chart*

RMS SUPPLY VOLTAGE. . . . . 6300 max. volts

DC BLOCKING VOLTAGE . . . . . 9000 max. volts

##### AVERAGE FORWARD CURRENT:

At free-air temperature of 60° C. . . . . 550 max. ma

At free-air temperature of 100° C. . . . . 210 max. ma

At other free-air temperatures. . . . . See *Average-Forward-  
 Current Rating Chart*

← Indicates a change.



# CR109

PEAK RECURRENT CURRENT. . . . .	5 max.	amp
PEAK SURGE CURRENT: <sup>b</sup>		
For one-half cycle, sine wave . . . . .	15 max.	amp
For one or more cycles, sine wave . . . . .	.See <i>Peak-Surge-Current Rating Chart</i>	
FREE-AIR TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +125	°C

## Characteristics:

Maximum Full-Cycle Average Forward Voltage Drop at maximum rated operating conditions. . . . .	9	volts
Instantaneous Forward Voltage Drop. . . . .	.See <i>Instantaneous Forward Characteristics Curve</i>	

## Maximum Reverse Current:

Dynamic (Averaged over one complete cycle at maximum ratings) <sup>c</sup> . . . . .	0.3	ma
DC (At maximum rated dc blocking voltage and any temperature within the operating temperature range). . . . .	0.6	ma

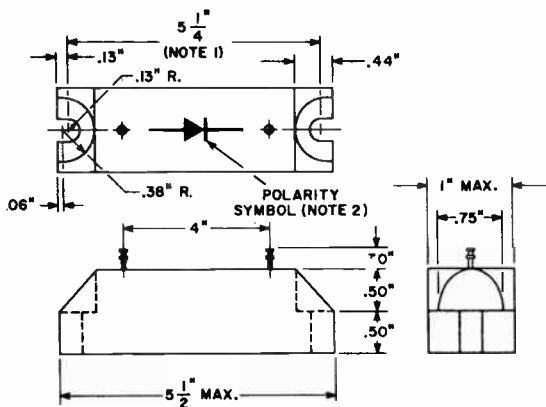
## Shunt Capacitance:

Maximum . . . . .	90	pf
Minimum . . . . .	45	pf

<sup>a</sup> See *Operating Considerations*.

<sup>b</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>c</sup> Example: For type CR109 at 60°C free-air temperature, average forward ma. = 550, peak reverse volts = 9000.



92CS-11250R1

NOTE 1: DISTANCE BETWEEN CENTERS OF MOUNTING HOLES FOR  $1/4$ "-DIAMETER BOLTS.

NOTE 2: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.



OPERATING CONSIDERATIONS,  
MECHANICAL AND ENVIRONMENTAL TESTS,  
RATING CHARTS,  
and  
CURVES

shown under type CR101 also apply to the CR109







## Silicon Rectifier

## With Integral R-C Voltage-Equalizing Network

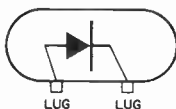
## DIFFUSED-JUNCTION TYPE

For Industrial and Military Equipment  
Designed to Meet Stringent Military Mechanical and Environmental Specifications

## GENERAL DATA

## Mechanical:

Operating Position<sup>a</sup>. . . . . Any  
Dimensions . . . . . See *Dimensional Outline Case*  
Material . . . . . Insulating  
Material flammability. . . . . Self-Quenching  
Seals. . . . . Hermetic  
Weight (Approx.) . . . . . 5.3 oz  
Terminal Diagram:



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

## HALF-WAVE RECTIFIER

## Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load, and at altitudes up to 30,000 feet

PEAK INVERSE VOLTAGE. . . . .	9000 max.	volts
RMS SUPPLY VOLTAGE. . . . .	6300 max.	volts
DC BLOCKING VOLTAGE . . . . .	9000 max.	volts
AVERAGE FORWARD CURRENT:		
At ambient temperature of 60° C . . . . .	550 max.	ma
At ambient temperature of 100° C. . . . .	210 max.	ma
At other ambient temperatures. . . . .	See <i>Average-Forward-Current Rating Chart</i>	
PEAK RECURRENT CURRENT. . . . .	5 max.	amp
PEAK SURGE CURRENT: <sup>b</sup>		
For one-half cycle, sine wave . . . . .	15 max.	amp
For one or more cycles. . . . .	See <i>Peak-Surge-Current Rating Chart</i>	
AMBIENT-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +125	°C



# CR109

## Characteristics:

Maximum Full-Cycle Average Forward Voltage

Drop at maximum rated operating conditions. . . . . 9 volts

Instantaneous Forward Voltage Drop .See *Instantaneous Forward Characteristics Curve*

Maximum Reverse Current:

Dynamic (averaged over one complete cycle at maximum ratings)<sup>c</sup>. . . . . 0.3 ma

DC at maximum rated dc blocking voltage and any temperature within the operating temperature range . . . . . 0.6 ma

Shunt Capacitance:

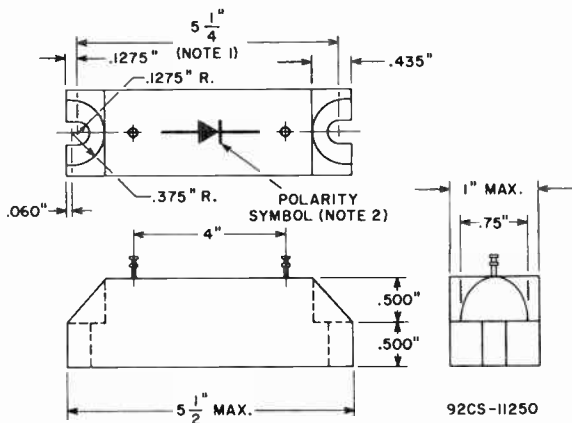
Maximum . . . . . 90  $\mu$ f

Minimum . . . . . 45  $\mu$ f

<sup>a</sup> See *Operating Considerations*.

<sup>b</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>c</sup> Example: For type CR109 at 60° C ambient temperature, average forward ma. = 550, peak inverse volts = 9000.



NOTE 1: DISTANCE BETWEEN CENTERS OF MOUNTING HOLES FOR 1/4"-DIAMETER BOLTS.

NOTE 2: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.

OPERATING CONSIDERATIONS,  
MECHANICAL AND ENVIRONMENTAL TESTS,  
RATING CHARTS,  
and  
CURVES

Shown under Type CR101 also apply to the CR109



## Silicon Rectifier

## With Integral R-C Voltage-Equalizing Network

## DIFFUSED-JUNCTION TYPE

For Industrial and Military Equipment

Designed to Meet Stringent Military Mechanical and Environmental Specifications

## GENERAL DATA

## Mechanical:

Operating Position <sup>a</sup> . . . . .	Any
Dimensions. . . . .	See <i>Dimensional Outline</i>
Case:	
Material. . . . .	Insulating
Material flammability . . . . .	Self-Quenching
Seals . . . . .	Hermetic
Weight (Approx.). . . . .	5.5 oz ←
Terminal Diagram:	←



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

## HALF-WAVE RECTIFIER

## Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load, and at altitudes up to 30,000 feet.

PEAK REVERSE VOLTAGE (Repetitive) . . . . .	10000 max.	volts ←
PEAK-TRANSIENT REVERSE VOLTAGE (Non-repetitive, for duration of 5-milliseconds maximum):		
At free-air temperature of +60° to +125° C. . . . .	12000 max.	volts
At other free-air temperatures. . . . .	See <i>Peak Transient Reverse Voltage Rating Chart</i>	
RMS SUPPLY VOLTAGE. . . . .	7000 max.	volts
DC BLOCKING VOLTAGE . . . . .	10000 max.	volts
AVERAGE FORWARD CURRENT:		
At free-air temperature of 60° C. . . . .	550 max.	ma
At free-air temperature of 100° C. . . . .	210 max.	ma
At other free-air temperatures. . . . .	See <i>Average-Forward- Current Rating Chart</i>	
PEAK RECURRENT CURRENT. . . . .	5 max.	amp

← Indicates a change.



# CR110

## PEAK SURGE CURRENT:<sup>b</sup>

For one-half cycle, sine wave . . . . . 15 max. amp  
 For one or more cycles, sine wave . . See *Peak-Surge-Current Rating Chart*

## FREE-AIR TEMPERATURE RANGE:

Operating and storage . . . . . -65 to +125 °C

## Characteristics:

### Maximum Full-Cycle Average Forward Voltage

Drop at maximum rated operating conditions . . 9.6 volts  
 Instantaneous Forward Voltage Drop . See *Instantaneous Forward Characteristics Curve*

### Maximum Reverse Current:

Dynamic (Averaged over one complete cycle at maximum ratings)<sup>c</sup>. . . . . 0.3 ma  
 DC (At maximum rated dc blocking voltage and any temperature within the operating temperature range). . . . . 0.6 ma

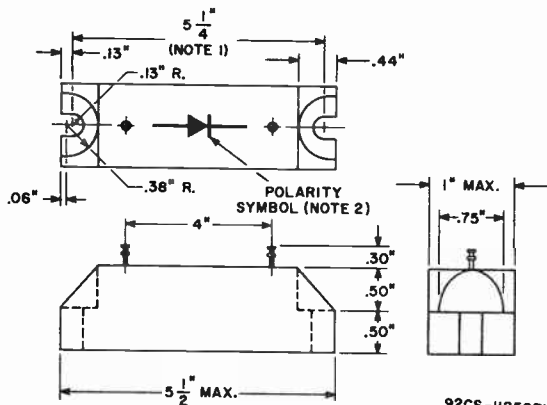
### Shunt Capacitance:

Maximum . . . . . 80 pf  
 Minimum . . . . . 40 pf

<sup>a</sup> See *Operating Considerations*.

<sup>b</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>c</sup> Example: For type CR110 at 60° C free-air temperature, average forward ma. = 550, peak reverse volts = 1000.



NOTE 1: DISTANCE BETWEEN CENTERS OF MOUNTING HOLES FOR 1/4"-DIAMETER BOLTS.

NOTE 2: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.



OPERATING CONSIDERATIONS,  
MECHANICAL AND ENVIRONMENTAL TESTS,  
RATING CHARTS,  
and  
CURVES

shown under type CR101 also apply to the CR110





## Silicon Rectifier

## With Integral R-C Voltage-Equalizing Network

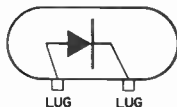
## DIFFUSED-JUNCTION TYPE

For Industrial and Military Equipment  
Designed to Meet Stringent Military Mechanical and Environmental Specifications

## GENERAL DATA

## Mechanical:

Operating Position <sup>a</sup> . . . . .	Any
Dimensions . . . . .	See <i>Dimensional Outline</i>
Case:	
Material . . . . .	Insulating
Material flammability . . . . .	Self-Quenching
Seals . . . . .	Hermetic
Weight (Approx.) . . . . .	5.3 oz
Terminal Diagram:	



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

## HALF-WAVE RECTIFIER

## Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load, and at altitudes up to 30,000 feet.

PEAK INVERSE VOLTAGE . . . . .	10000 max.	volts
RMS SUPPLY VOLTAGE . . . . .	7000 max.	volts
DC BLOCKING VOLTAGE . . . . .	10000 max.	volts
AVERAGE FORWARD CURRENT:		
At ambient temperature of 60° C . . . . .	550 max.	ma
At ambient temperature of 100° C . . . . .	210 max.	ma
At other ambient temperatures . . . . .	See <i>Average-Forward-Current Rating Chart</i>	
PEAK RECURRENT CURRENT . . . . .	5 max.	amp
PEAK SURGE CURRENT: <sup>b</sup>		
For one-half cycle, sine wave . . . . .	15 max.	amp
For one or more cycles. See <i>Peak-Surge-Current Rating Chart</i>		
AMBIENT-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +125	°C



# CR110

## Characteristics:

### Maximum Full-Cycle Average Forward Voltage

Drop at maximum rated operating conditions. . . . . 9.6 volts

Instantaneous Forward Voltage Drop .See *Instantaneous Forward Characteristics Curve*

### Maximum Reverse Current:

Dynamic (averaged over one complete cycle at maximum ratings)<sup>a</sup>. . . . . 0.3 ma

DC at maximum rated dc blocking voltage and any temperature within the operating temperature range . . . . . 0.6 ma

### Shunt Capacitance:

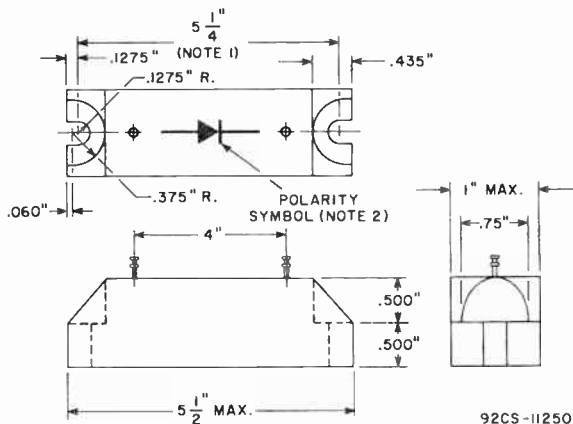
Maximum . . . . . 80  $\mu$ f

Minimum . . . . . 40  $\mu$ f

<sup>a</sup> See *Operating Considerations*.

<sup>b</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>c</sup> Example: For type CR110 at 60<sup>o</sup> C ambient temperature, average forward ma. = 550, peak inverse volts = 10000.



NOTE 1: DISTANCE BETWEEN CENTERS OF MOUNTING HOLES FOR 1/4"-DIAMETER BOLTS.

NOTE 2: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.

OPERATING CONSIDERATIONS,  
MECHANICAL AND ENVIRONMENTAL TESTS,  
RATING CHARTS,  
and  
CURVES

Shown under Type CR101 also apply to the CR110





## Silicon Rectifier

With Precisely-Matched Cells  
for Internal Voltage Equalization

### DIFFUSED-JUNCTION TYPE

For Industrial and Military Equipment

Designed to Meet Stringent Electrical, Mechanical, and Environmental Specifications

### GENERAL DATA

#### Mechanical:

Operating Position. . . . . Any  
 Dimensions. . . . . See *Dimensional Outline*  
 Case:  
 Material. . . . . Insulating  
 Material flammability . . . . . Self-Quenching  
 Seals . . . . . Hermetic  
 Weight (Approx.). . . . . 0.32 oz  
 Terminal Diagram:



The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

### HALF-WAVE RECTIFIER

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load

PEAK REVERSE VOLTAGE. . . . . 1500 max. volts  
 RMS SUPPLY VOLTAGE. . . . . 1060 max. volts  
 DC BLOCKING VOLTAGE . . . . . 1500 max. volts  
 AVERAGE FORWARD CURRENT:  
 At free-air temperature of 60° C. . . . . 300 max. ma  
 At free-air temperature of 100° C . . . . . 115 max. ma  
 At other free-air temperatures. . . . . See *Average-Forward-Current Rating Chart*  
 PEAK RECURRENT CURRENT. . . . . 3 max. amp  
 PEAK SURGE CURRENT:<sup>a</sup>  
 For one-half cycle, sine wave . . . . . 9 max. amp  
 For one or more cycles, sine wave . . . . . See *Peak-Surge-Current Rating Chart*  
 FREE-AIR TEMPERATURE RANGE:  
 Operating and storage . . . . . -65 to +125 °C



# CR201

## Characteristics:

Maximum Full-Cycle Average Forward Voltage Drop at maximum-rated operating conditions. . . . . 1.8 volts  
Instantaneous Forward Voltage Drop: See *Instantaneous Forward Characteristics Curve*

## Maximum-Reverse Current:

Dynamic (Averaged over one complete cycle at maximum ratings)<sup>b</sup>. . . . . 0.1 ma  
DC (At maximum rated dc blocking voltage and any temperature within the operating temperature range) free-air temperature =  
25° C . . . . . 0.01 ma  
100° C. . . . . 0.2 ma

<sup>a</sup> Superimposed on device operating within the maximum voltage, current, and temperature ratings and may be repeated after sufficient time has elapsed for the device to return to the presurge thermal-equilibrium conditions.

<sup>b</sup> Example: For type CR201 at 60° C free-air temperature, average forward ma. = 300, peak reverse volts = 1500.

## OPERATING CONSIDERATIONS

A *surge-limiting impedance* should always be used in series with the rectifier. The impedance value must be sufficient to limit the surge current to the value specified under the maximum ratings. This impedance may be provided by the power transformer windings, or by an external resistor or choke.

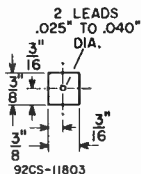
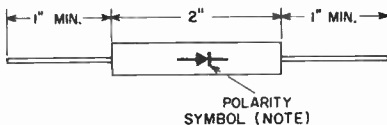
Because this rectifier operates at voltages which are dangerous, care should be taken in the design and operation of the equipment to prevent personnel from coming in contact with the rectifier.

Care should be exercised during the soldering operation to prevent overheating of the rectifier terminals. A clean, well-tinned iron is recommended to keep soldering time to a minimum.

During a period of prolonged heating, for example, during lead unwrapping, a heat sink such as the jaws of a pair of long-nose pliers should be used between the tip of the soldering iron and the rectifier case.

This rectifier should not be used in series arrangements to obtain dc output voltages higher than those obtained from a single unit. For information on special precision-matched units for use in such series arrangements, write to RCA, Commercial Engineering, Somerville, New Jersey.





NOTE: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.

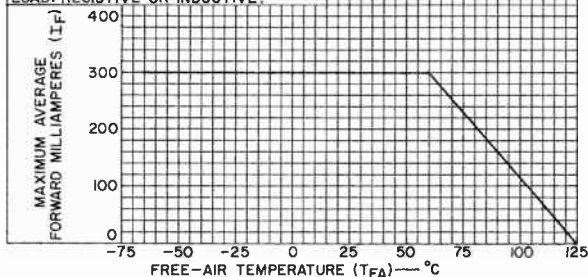


## AVERAGE-FORWARD-CURRENT RATING CHART

FOR DC AND POLYPHASE OPERATION,  
MULTIPLY MAXIMUM-AVERAGE-FORWARD-  
CURRENT RATING FOR EACH RECTIFIER  
BY THE FOLLOWING FACTOR:

TYPE OF OPERATION	FACTOR
DIRECT CURRENT	1.10
THREE PHASE	0.89
SIX PHASE	0.68

LOAD: RESISTIVE OR INDUCTIVE.

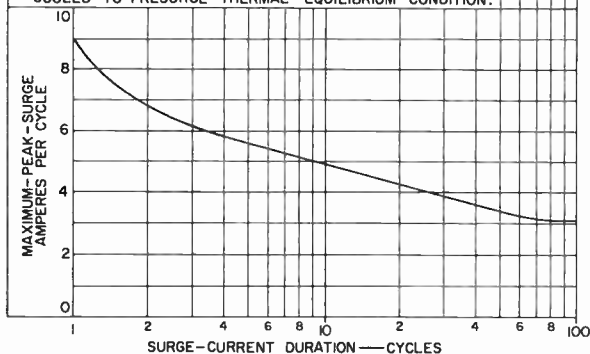


92CS-11704

## PEAK-SURGE-CURRENT RATING CHART

SUPPLY FREQUENCY = 60 CPS SINE WAVE  
LOAD: RESISTIVE OR INDUCTIVE.

PEAK SURGE CURRENT (SUPERIMPOSED ON STEADY-STATE  
CURRENT FOR DEVICE OPERATING WITHIN MAXIMUM  
RATINGS) MAY BE REPEATED AFTER THE DEVICE HAS  
COOLED TO PRESURGE THERMAL-EQUILIBRIUM CONDITION.



92CS-11706



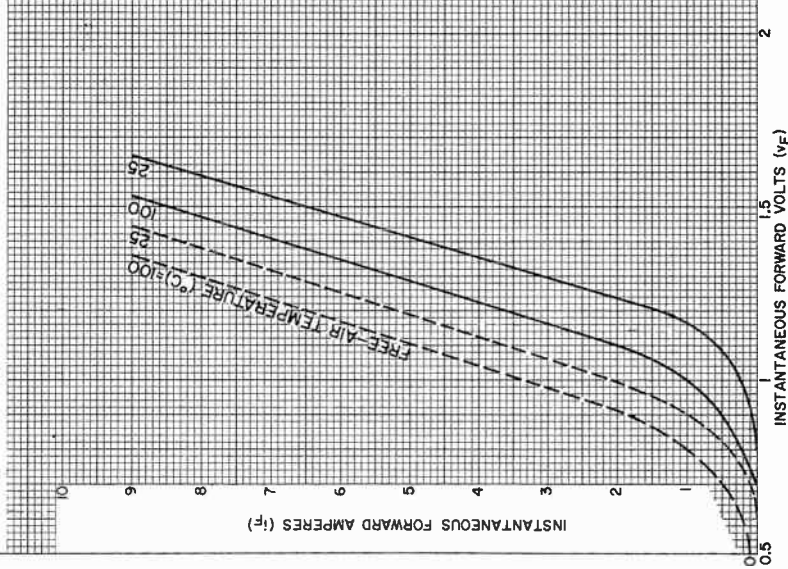
# INSTANTANEOUS FORWARD CHARACTERISTICS

## Typical and Maximum Values

TO DETERMINE  $v_f$  FOR EACH RECTIFIER TYPE: MULTIPLY VALUE GIVEN AT INTERSECTION OF CURVE FOR THE APPROPRIATE TEMPERATURE WITH THE DESIRED VALUE OF  $i_f$  BY THE FOLLOWING FACTOR:

RCA TYPE	FACTOR
CR201	3
CR203	5
CR204	6
CR206	10
CR208	10
CR210	12
CR212	12

— MAXIMUM  
- - - TYPICAL





## Silicon Rectifier

With Precisely-Matched Cells  
for Internal Voltage Equalization

### DIFFUSED-JUNCTION TYPE

For Industrial and Military Equipment  
Designed to Meet Stringent Electrical, Mechanical, and Environmental Specifications

The CR203 is the same as the CR201 except for the following items:

#### Mechanical:

Dimensions. . . . . See Dimensional Outline  
Weight (Approx.). . . . . 0.55 oz

### HALF-WAVE RECTIFIER

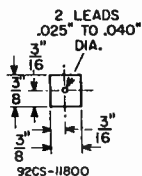
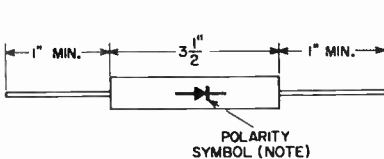
Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load

PEAK REVERSE VOLTAGE. . . . .	1500 max.	volts
RMS SUPPLY VOLTAGE. . . . .	1060 max.	volts
DC BLOCKING VOLTAGE. . . . .	1500 max.	volts

#### Characteristics:

Maximum Full-Cycle Average Forward Voltage Drop at maximum-rated operating conditions. . . . .	3	volts
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NOTE: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.







## Silicon Rectifier

With Precisely-Matched Cells  
for Internal Voltage Equalization

### DIFFUSED-JUNCTION TYPE

For Industrial and Military Equipment  
Designed to Meet Stringent Electrical, Me-  
chanical, and Environmental Specifications

The CR204 is the same as the CR201 except for the following items:

#### Mechanical:

Dimensions. . . . . See Dimensional Outline  
Weight (Approx.). . . . . 0.73 oz

### HALF-WAVE RECTIFIER

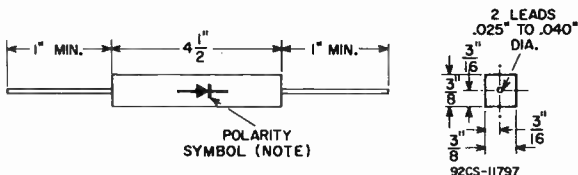
Maximum and Minimum Ratings, Absolute-Maximum Values:

*For power-supply frequency of 60 cps, single-  
phase operation, with resistive or inductive load*

PEAK REVERSE VOLTAGE. . . . .	3000 max.	volts
RMS SUPPLY VOLTAGE. . . . .	2120 max.	volts
DC BLOCKING VOLTAGE. . . . .	3000 max.	volts

#### Characteristics:

Maximum Full-Cycle Average Forward Voltage Drop at maximum-rated operating conditions. . . . .	3.6	ma
--	-----	----



NOTE: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT  
FLOW AS INDICATED BY DC AMMETER.





## Silicon Rectifier

With Precisely-Matched Cells  
for Internal Voltage Equalization

DIFFUSED-JUNCTION TYPE

For Industrial and Military Equipment

Designed to Meet Stringent Electrical, Mechanical, and Environmental Specifications

The CR206 is the same as the CR201 except for the following items:

### Mechanical:

Dimensions. . . . . See Dimensional Outline  
Weight (Approx.). . . . . 1.20 oz

### HALF-WAVE RECTIFIER

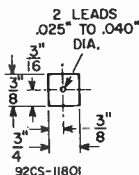
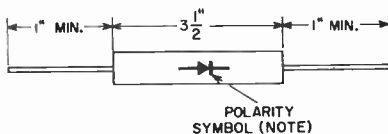
Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load

PEAK REVERSE VOLTAGE. . . . .	6000 max.	volts
RMS SUPPLY VOLTAGE. . . . .	4240 max.	volts
DC BLOCKING VOLTAGE . . . . .	6000 max.	volts

### Characteristics:

Maximum Full-Cycle Average Forward Voltage Drop at maximum-rated operating conditions. . . . .	6	volts
--	---	-------



NOTE: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.





## Silicon Rectifier

With Precisely-Matched Cells  
for Internal Voltage Equalization

### DIFFUSED-JUNCTION TYPE

For Industrial and Military Equipment  
Designed to Meet Stringent Electrical, Mechanical, and Environmental Specifications

The CR208 is the same as the CR201 except for the following items:

#### Mechanical:

Dimensions. . . . . See Dimensional Outline  
Weight (Approx.). . . . . 1.20 oz

### HALF-WAVE RECTIFIER

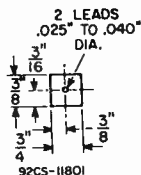
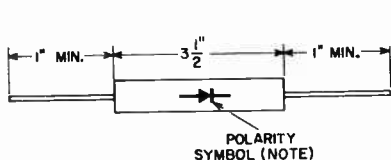
Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load

PEAK REVERSE VOLTAGE. . . . . 8000 max. volts  
RMS SUPPLY VOLTAGE. . . . . 5650 max. volts  
DC BLOCKING VOLTAGE . . . . . 8000 max. volts

#### Characteristics:

Maximum Full-Cycle Average Forward Voltage Drop at maximum-rated operating conditions. . . . . 6 volts



**NOTE:** ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.





## Silicon Rectifier

With Precisely-Matched Cells  
for Internal Voltage Equalization

DIFFUSED-JUNCTION TYPE

For Industrial and Military Equipment

Designed to Meet Stringent Electrical, Mechanical, and Environmental Specifications

The CR210 is the same as the CR201 except for the following items:

### Mechanical:

Dimensions. . . . . See Dimensional Outline  
Weight (Approx.). . . . . 1.60 oz

### HALF-WAVE RECTIFIER

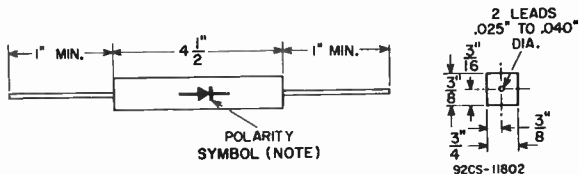
Maximum and Minimum Ratings, Absolute-Maximum Values:

*For power-supply frequency of 60 cps, single-phase operation, with resistive or inductive load*

PEAK REVERSE VOLTAGE. . . . .	10000 max.	volts
RMS SUPPLY VOLTAGE. . . . .	7070 max.	volts
DC BLOCKING VOLTAGE . . . . .	10000 max.	volts

### Characteristics:

Maximum Full-Cycle Average Forward Voltage Drop at maximum-rated operating conditions. . . . .	7.2	volts
--	-----	-------



NOTE: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT FLOW AS INDICATED BY DC AMMETER.







## Silicon Rectifier

### With Precisely-Matched Cells for Internal Voltage Equalization

#### DIFFUSED-JUNCTION TYPE

For Industrial and Military Equipment  
Designed to Meet Stringent Electrical, Me-  
chanical, and Environmental Specifications

The CR212 is the same as the CR201 except for the following items:

#### Mechanical:

Dimensions. . . . . See Dimensional Outline  
Weight (Approx.). . . . . 1.60 oz

#### HALF-WAVE RECTIFIER

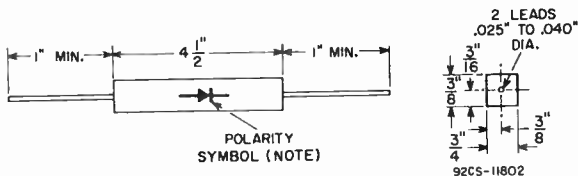
#### Maximum and Minimum Ratings, Absolute-Maximum Values:

For power-supply frequency of 60 cps, single-  
phase operation, with resistive or inductive load

PEAK REVERSE VOLTAGE. . . . .	12000 max.	volts
RMS SUPPLY VOLTAGE. . . . .	8480 max.	volts
DC BLOCKING VOLTAGE . . . . .	12000 max.	volts

#### Characteristics:

Maximum Full-Cycle Average Forward  
Voltage Drop at maximum-rated  
operating conditions. . . . . 7:2 max. volts



NOTE: ARROW INDICATES DIRECTION OF FORWARD (EASY) CURRENT  
FLOW AS INDICATED BY DC AMMETER.





## Twin Semiconductor Diode

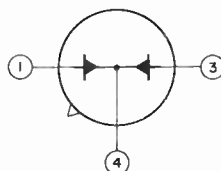
GERMANIUM DIFFUSED-JUNCTION TYPE  
For Switching Applications in Electronic Data-Processing Systems

## GENERAL DATA

## Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter . . . . .	0.370"
Dimensional Outline . . . . .	Similar to JEDEC No. TO-33 except that lead 2 is omitted
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See Dimensional Outline
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Diode  
Unit  
No. 1  
Lead 3 - Diode  
Unit  
No. 2



Lead 4 - Common  
Lead for  
Diode  
Units  
No. 1 &  
No. 2

The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.

## SWITCHING SERVICE

Values are for Each Unit

Maximum and Minimum Ratings, Absolute-Maximum Values:

At free-air temperature of 25° C unless otherwise specified

DC REVERSE VOLTAGE . . . . .	-20 max.	volts
DC FORWARD CURRENT <sup>a</sup> . . . . .	40 max.	ma
FREE-AIR TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +85	°C
LEAD TEMPERATURE:		
For 10 seconds maximum . . . . .	230 max.	°C

## ELECTRICAL CHARACTERISTICS

Values are for each unit and at free-air temperature of 25° C unless otherwise specified

	Min.	Max.	
DC Forward Voltage for dc forward ma. =			V <sub>F</sub>
5 . . . . .	-	0.4	volt
9 . . . . .	-	0.55	volt

<sup>a</sup> See accompanying Rating Chart.



# 2DG001

Reverse Breakdown Voltage for dc reverse $\mu\text{a} = -200$ . . . . .	$BV_R$	-20	-	volts
DC Forward Current for dc forward volts = 1 . . . . .	$I_F$	40	-	ma
DC Reverse Current at free-air temperature of $55^\circ\text{C}$ , for dc reverse volts =	$I_R$			
-2 . . . . .		-	-15	$\mu\text{a}$
-10 . . . . .		-	-75	$\mu\text{a}$
Reverse Recovery Time <sup>b</sup> for dc reverse volts = -6, dc forward ma. = 20, recovery to a reverse impedance (ohms) =	$t_{rr}$			
35000 . . . . .		-	0.25	$\mu\text{sec}$
82000 . . . . .		-	0.3	$\mu\text{sec}$

<sup>b</sup> See accompanying *Reverse-Recovery-Time Measurement Circuit*.

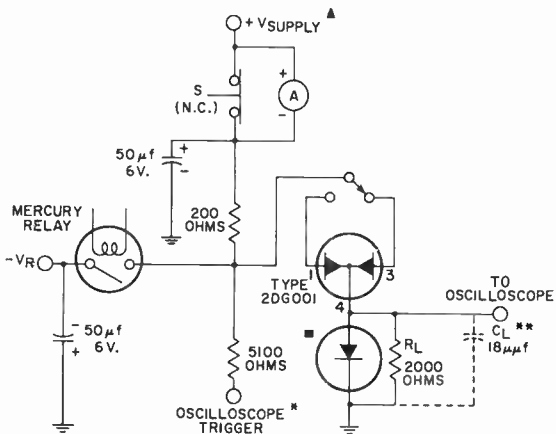
## OPERATING CONSIDERATIONS

It is recommended that this device not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the device or its associated circuitry.

The *flexible leads* of this device are usually soldered to the circuit elements. Soldering of the leads may be made close to the stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the device.



## REVERSE-RECOVERY-TIME MEASUREMENT CIRCUIT



92CS-11246

NOTE: THE STRAY CAPACITANCE ACROSS THE SOCKET FOR THE TWIN DIODE UNIT UNDER TEST MUST BE LESS THAN  $2 \mu\mu\text{f}$ .

\* TEKTRONIX TYPE 545 OSCILLOSCOPE WITH TYPE H PLUG-IN VERTICAL AMPLIFIER AND TYPE P6000 PROBE, OR EQUIVALENT.

\*\*  $C_L$  REPRESENTS THE TOTAL CAPACITANCE ACROSS  $R_L$  — THAT IS, THE SUM OF THE OSCILLOSCOPE-PROBE CAPACITANCE AND THE STRAY CAPACITANCE. THE STRAY CAPACITANCE ACROSS  $R_L$  MUST BE LESS THAN  $6 \mu\mu\text{f}$ .

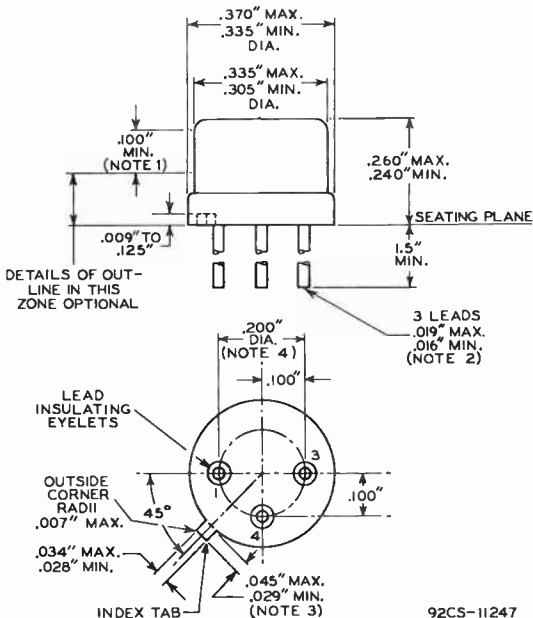
■ SILICON ULTRA-FAST SWITCHING DIODE WITH  $0.5\text{-}\mu\mu\text{sec}$  MAXIMUM REVERSE RECOVERY TIME WHEN SWITCHING FROM  $10 \text{ MA.}$  FORWARD CURRENT TO  $-6 \text{ VOLTS}$  REVERSE VOLTAGE.

▲ WITH RELAY OUT AND SWITCH (S) OPEN, ADJUST  $V_{\text{SUPPLY}}$  TO OBTAIN SPECIFIED FORWARD CURRENT ( $I_F$ ).



# 2DG001

SIMILAR TO JEDEC No. T0-33  
except lead 2 is omitted



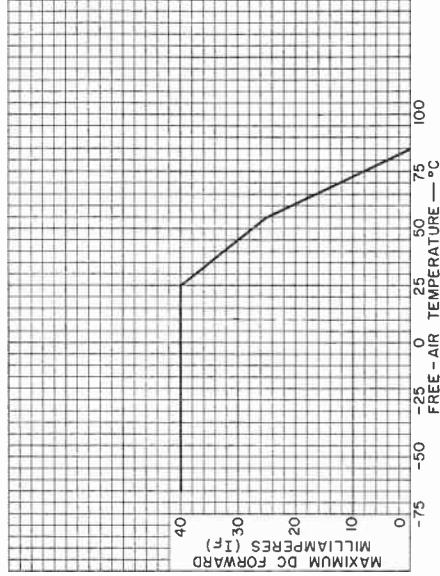
NOTE 1: THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE VARIATION IN ACTUAL DIAMETER WITHIN THE ZONE SHALL NOT EXCEED 0.010".

NOTE 2: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE SEATING PLANE. BETWEEN 0.25" AND 1.5" A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

NOTE 3: MEASURED FROM MAXIMUM DIAMETER OF THE ACTUAL DEVICE.

NOTE 4: LEADS HAVING MAXIMUM DIAMETER (0.019") MEASURED IN GAUGING PLANE 0.054" + 0.001" - 0.000" BELOW THE SEATING PLANE OF THE DEVICE SHALL BE WITHIN 0.007" OF THEIR TRUE LOCATIONS RELATIVE TO A MAXIMUM-WIDTH TAB.

## RATING CHART



92CS-11198









2N32

2N32

# POINT-CONTACT TRANSISTOR

GERMANIUM TYPE FOR PULSE OR SWITCHING APPLICATIONS

## DATA

### General:

Maximum Overall Length . . . . .	0.660"
Maximum Seated Length . . . . .	0.445"
Width . . . . .	0.320" ± 0.020"
Maximum Depth . . . . .	0.240"
Case . . . . .	Plastic
Base . . . . .	Small-Oblong Linotetar 3-Pin
Mounting Position . . . . .	Any

## PULSE or SWITCHING SERVICE

*Voltage values are given with respect to base connection*

### Maximum Ratings, Absolute Values:

#### COLLECTOR:

DC Voltage . . . . .	-40 max.	volts
DC Current . . . . .	-8 max.	ma
Dissipation . . . . .	50 max.	mW

#### EMITTER:

DC Voltage . . . . .	-40 max.	volts
DC Current . . . . .	3 max.	ma

AMBIENT TEMPERATURE . . . . . 40 max. °C

### Characteristics at Ambient Temperature of 25°C:

*With input circuit between emitter and base connection, and output circuit between collector and base connection*

DC Collector Voltage . . . . .	-25	volts
DC Emitter Current <sup>o</sup> . . . . .	0.5	ma
Current Amplification Factor . . . . .	2.2	

#### Resistance:

Open-Circuit Input . . . . .	400	ohms
Open-Circuit Output . . . . .	31000	ohms
Feedback . . . . .	140	ohms

Power Gain# . . . . . 21 db

#### Frequency:

For voltage-gain cutoff† . . . . .	0.9	Mc
For alpha cutoff†† . . . . .	2.7	Mc

### Minimum Circuit Values:

Emitter-Circuit Resistance . . . . . 1000 min. ohms

<sup>o</sup> obtained by adjusting a variable resistor in series with power supply to give the desired current.

# with collector load resistance of 10000 ohms, signal-source impedance of 500 ohms, and signal frequency of 5000 cycles per second.

† measured at a point 3 decibels down from the low-frequency value (100 kc) and with collector load resistance of 20000 ohms, signal-source impedance of 300 ohms, and signal voltage of 25 millivolts rms. The cutoff frequency is defined as the frequency at which the output voltage has dropped to 0.7 of its low-frequency value.

††, see next page.

2N32



2N32

## POINT-CONTACT TRANSISTOR

†† Measured at a point 3 decibels down from its low-frequency value (100 kc). The cutoff frequency is defined as the frequency at which the current amplification factor has dropped to 0.7 of its low-frequency value.

*The 2N32 should not be inserted into or withdrawn from its socket with the power "on" because high transient currents may cause permanent damage to the transistor.*

JUNE 1, 1953

TUBE DEPARTMENT

RADIO CORPORATION OF AMERICA, HARRISON, NEW JERSEY

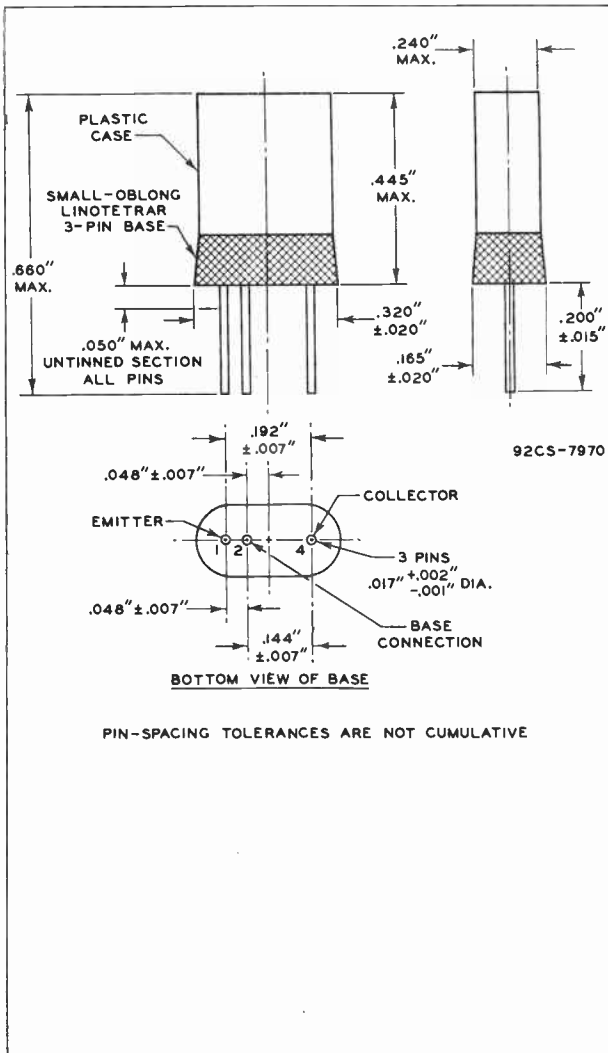
TENTATIVE DATA



2N32

2N32

# POINT-CONTACT TRANSISTOR



JUNE 1, 1953

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CE-7970

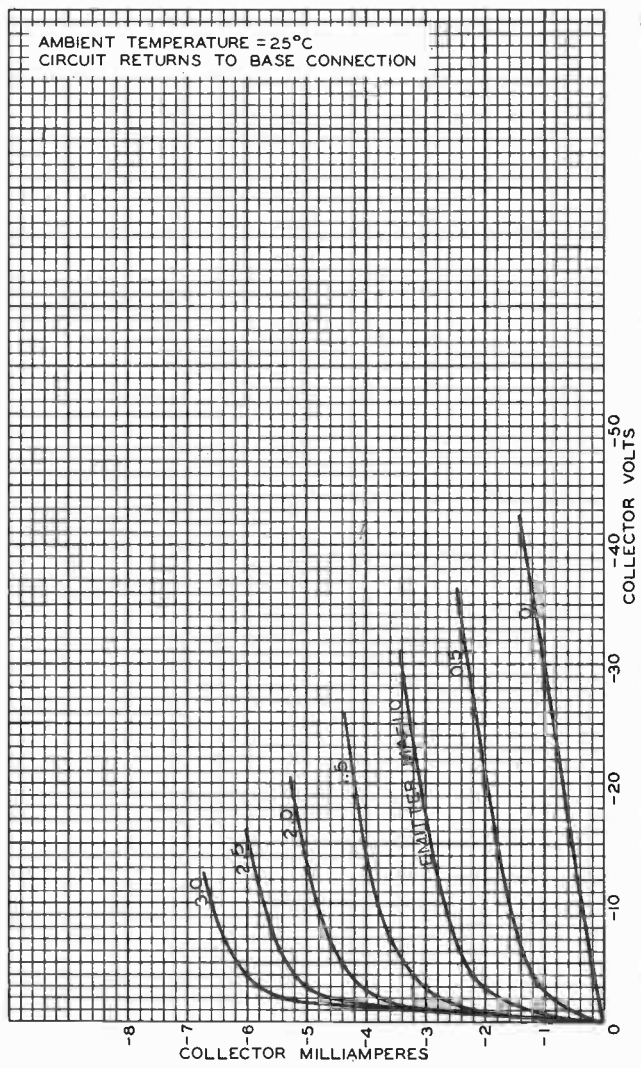
2N32



2N32

### AVERAGE COLLECTOR CHARACTERISTICS

AMBIENT TEMPERATURE = 25°C  
CIRCUIT RETURNS TO BASE CONNECTION



APR. 8, 1953

TUBE DEPARTMENT  
RADIO CORPORATION OF AMERICA, HARRISON, NEW JERSEY

92CM-7963



2N33

2N33

# POINT-CONTACT TRANSISTOR

GERMANIUM TYPE FOR OSCILLATOR APPLICATIONS UP TO 50 Mc

## DATA

### General:

Maximum Overall Length . . . . .	0.660"
Maximum Seated Length . . . . .	0.445"
Width . . . . .	0.320" ± 0.020"
Maximum Depth . . . . .	0.240"
Case . . . . .	Plastic
Base . . . . .	Small-Oblong Linotetrar 3-Pin
Mounting Position . . . . .	Any

## VHF OSCILLATOR SERVICE

*Voltage values are given with respect to base connection*

### Maximum Ratings, Absolute Values:

COLLECTOR:		
DC Voltage . . . . .	-8.5 max.	volts
DC Current . . . . .	-7 max.	ma
Dissipation . . . . .	30 max.	mw
EMITTER:		
DC Current . . . . .	0.8 max.	ma
AMBIENT TEMPERATURE . . . . .	40 max.	°C

### Typical Operation in Accompanying 50-Mc Oscillator Test Circuit:

COLLECTOR:		
DC Supply Voltage . . . . .	-8	volts
DC Current . . . . .	-3.3	ma
DC Emitter Current . . . . .	0.3	ma
Useful Power Output (Approx.) . . . . .	1.0	mw

*The 2N33 should not be inserted into or withdrawn from its socket with the power "on" because high transient currents may cause permanent damage to the transistor.*

OUTLINE DIMENSIONS and TERMINAL CONNECTIONS for Type 2N33 are the same as those shown for Type 2N32

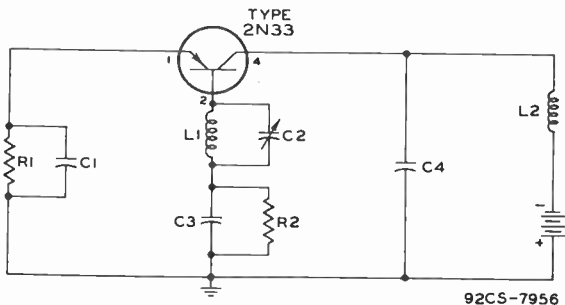
2N33



2N33

## POINT-CONTACT TRANSISTOR

50-Mc Oscillator Test Circuit



92CS-7956

C1: 1  $\mu\text{f}$ , ceramic, 25 volts  
 C2: 4 to 30  $\mu\text{f}$ , ceramic adjustable, 25 volts  
 C3: 270  $\mu\text{f}$ , mica, 25 volts

C4: 470  $\mu\text{f}$ , mica, 25 volts  
 L1: 0.46  $\mu\text{h}$  tank inductance  
 L2: 1 mh rf choke  
 R1: 5100 ohms, 0.5 watt  
 R2: 1000 ohms, 0.5 watt

Devices and arrangements shown or described herein may use patents of RCA or others. Information contained herein is furnished without responsibility by RCA for its use and without prejudice to RCA's patent rights.

JUNE 1, 1953

TUBE DEPARTMENT

CE-7956

RADIO CORPORATION OF AMERICA, HARRISON, NEW JERSEY

World Radio History



2N34

2N34

# JUNCTION TRANSISTOR

P-N-P GERMANIUM TYPE

FOR LOW-POWER, LOW-FREQUENCY APPLICATIONS

## DATA

### General:

Maximum Overall Length . . . . .	0.885"
Maximum Seated Length . . . . .	0.670"
Width . . . . .	0.320" ± 0.020"
Depth . . . . .	0.165" ± 0.020"
Case . . . . .	Plastic
Base . . . . .	Small-Oblong Linotetrar 3-Pin
Mounting Position . . . . .	Any

## AUDIO-FREQUENCY AMPLIFIER SERVICE

*Voltages are given with respect to base connection*

### Maximum Ratings, Absolute Values:

#### COLLECTOR:

DC Voltage . . . . .	-25 max.	volts
DC Current . . . . .	-8 max.	ma
Dissipation . . . . .	50 max.	mw

#### EMITTER:

DC Current . . . . .	8 max.	ma
----------------------	--------	----

AMBIENT TEMPERATURE . . . . .	50 max.	°C
-------------------------------	---------	----

### Characteristics at Ambient Temperature of 25°C:

*With input circuit between base connection and emitter, and output circuit between collector and emitter*

#### Collector:

DC Voltage . . . . .	-6	volts
DC Current . . . . .	-10 <sup>▲</sup>	μamp
DC Emitter Current* . . . . .	1	ma
DC Base-Connection Current . . . . .	-25	μamp

#### Current Amplification Factor (Approx.):

Between Emitter and Collector . . . . .	0.98
Between Base Connection and Collector . . . . .	40

Power Gain# . . . . .	40	db
-----------------------	----	----

<sup>▲</sup> with collector voltage of -12 volts and emitter current of 0 milli-amperes.

\* obtained by adjusting a variable resistor in series with the power supply to give the desired current.

# with collector load resistance of 30000 ohms, signal-source impedance of 500 ohms, and signal frequency of 5000 cycles per second.

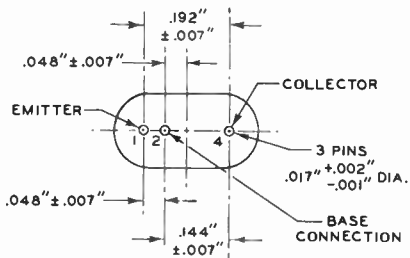
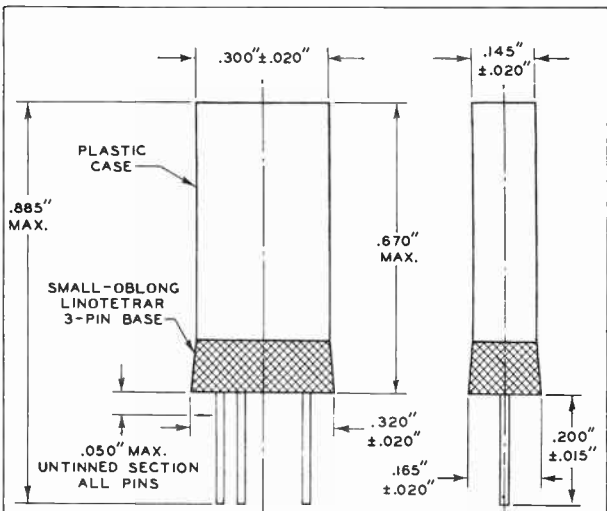
*The 2N34 should not be inserted into or withdrawn from its socket with the power "on" because high transient currents may cause permanent damage to the transistor.*

2N34



2N34

JUNCTION TRANSISTOR



92CS-7972

BOTTOM VIEW OF BASE

PIN-SPACING TOLERANCES ARE NOT CUMULATIVE



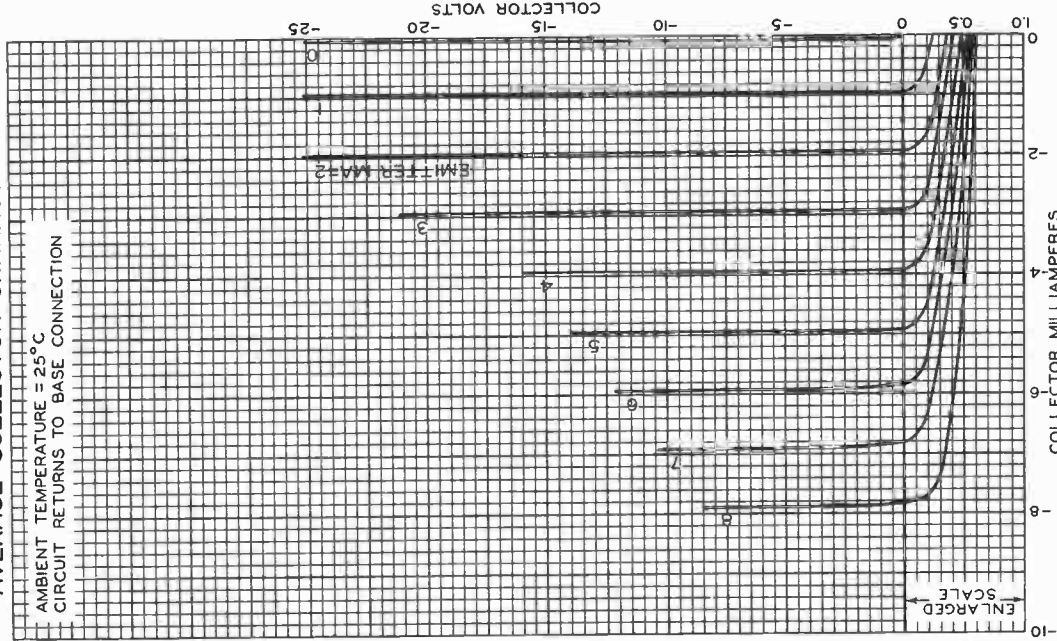


2N34

2N34

# AVERAGE COLLECTOR CHARACTERISTICS

AMBIENT TEMPERATURE = 25°C  
CIRCUIT RETURNS TO BASE CONNECTION



APR. 8, 1953

TUBE DEPARTMENT

RADIO CORPORATION OF AMERICA, HARRISON, NEW JERSEY

92CM-7962

2N34

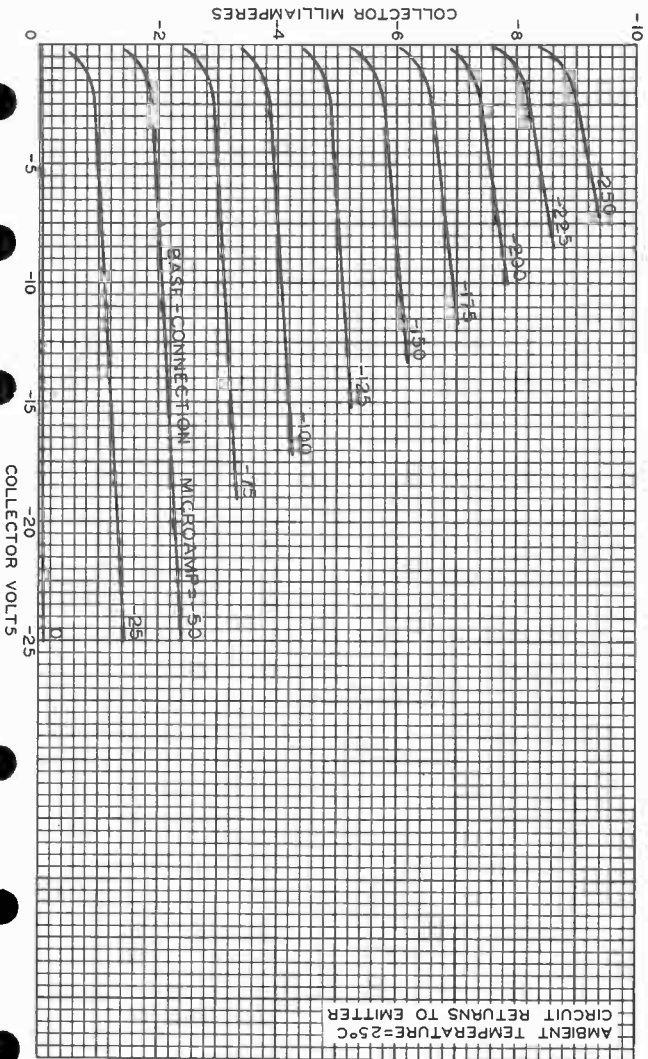
2N34



World Radio History

### AVERAGE COLLECTOR CHARACTERISTICS

AMBIENT TEMPERATURE = 25°C  
CIRCUIT RETURNS TO EMITTER



92CM-7961

TUBE DEPARTMENT  
RADIO CORPORATION OF AMERICA, HARRISON, NEW JERSEY

APR. 8, 1953



2N35

2N35

# JUNCTION TRANSISTOR

N-P-N GERMANIUM TYPE  
FOR LOW-POWER, LOW-FREQUENCY APPLICATIONS

## DATA

### General:

Maximum Overall Length . . . . .	0.885"
Maximum Seated Length . . . . .	0.670"
Width . . . . .	0.320" ± 0.020"
Depth . . . . .	0.165" ± 0.020"
Case . . . . .	Plastic
Base . . . . .	Small-Oblong Linotetrar 3-Pin
Mounting Position . . . . .	Any

## AUDIO-FREQUENCY AMPLIFIER SERVICE

*Voltages are given with respect to base connection*

### Maximum Ratings, Absolute Values:

#### COLLECTOR:

DC Voltage . . . . .	25 max.	volts
DC Current . . . . .	8 max.	ma
Dissipation . . . . .	50 max.	mw

#### EMITTER:

DC Current . . . . .	-8 max.	ma
----------------------	---------	----

AMBIENT TEMPERATURE . . . . .	50 max.	°C
-------------------------------	---------	----

### Characteristics at Ambient Temperature of 25°C:

*With input circuit between base connection and emitter,  
and output circuit between collector and emitter*

#### Collector:

DC Voltage . . . . .	6	volts
DC Current . . . . .	10 <sup>▲▲</sup>	μamp
DC Emitter Current* . . . . .	-1	ma
DC Base-Connection Current . . . . .	25	μamp

#### Current Amplification Factor (Approx.):

Between Emitter and Collector . . . . .	0.98	
Between Base Connection and Collector . . . . .	40	
Power Gain# . . . . .	40	db

<sup>▲▲</sup> with collector voltage of 12 volts and emitter current of 0 milli-amperes.

\* obtained by adjusting a variable resistor in series with the power supply to give the desired current.

# with collector load resistance of 30000 ohms, signal-source impedance of 500 ohms, and signal frequency of 5000 cycles per second.

*The 2N35 should not be inserted into or withdrawn from its socket with the power "on" because high transient currents may cause permanent damage to the transistor.*

OUTLINE DIMENSIONS and TERMINAL CONNECTIONS  
for Type 2N35 are the same as those shown for Type 2N34



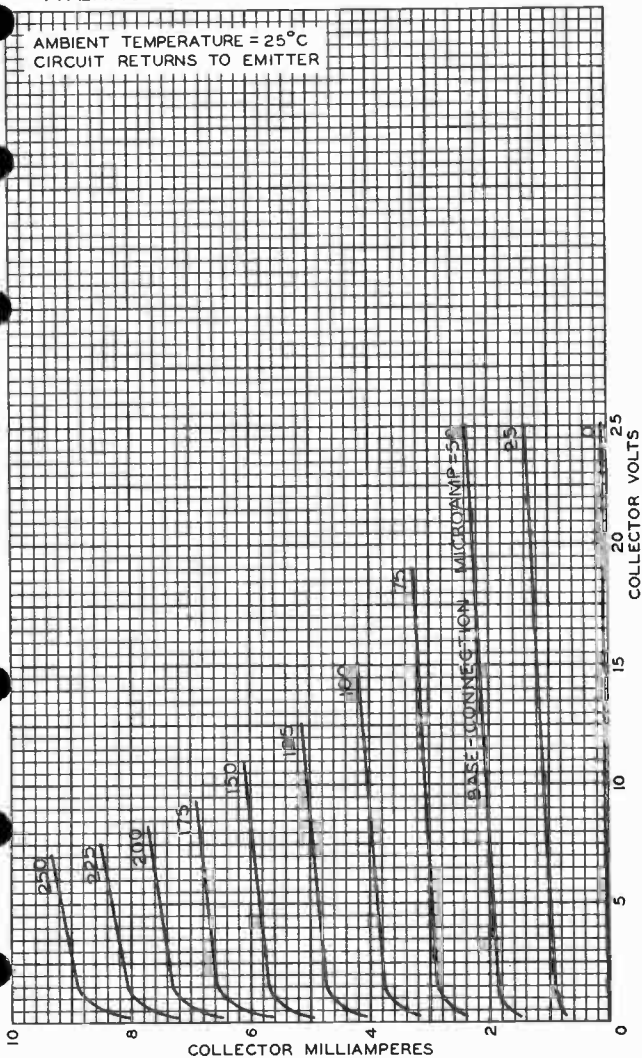


2N35

2N35

# AVERAGE COLLECTOR CHARACTERISTICS

AMBIENT TEMPERATURE = 25°C  
CIRCUIT RETURNS TO EMITTER



APR. 7, 1953

TUBE DEPARTMENT  
RADIO CORPORATION OF AMERICA, HARRISON, NEW JERSEY

92CM-7959

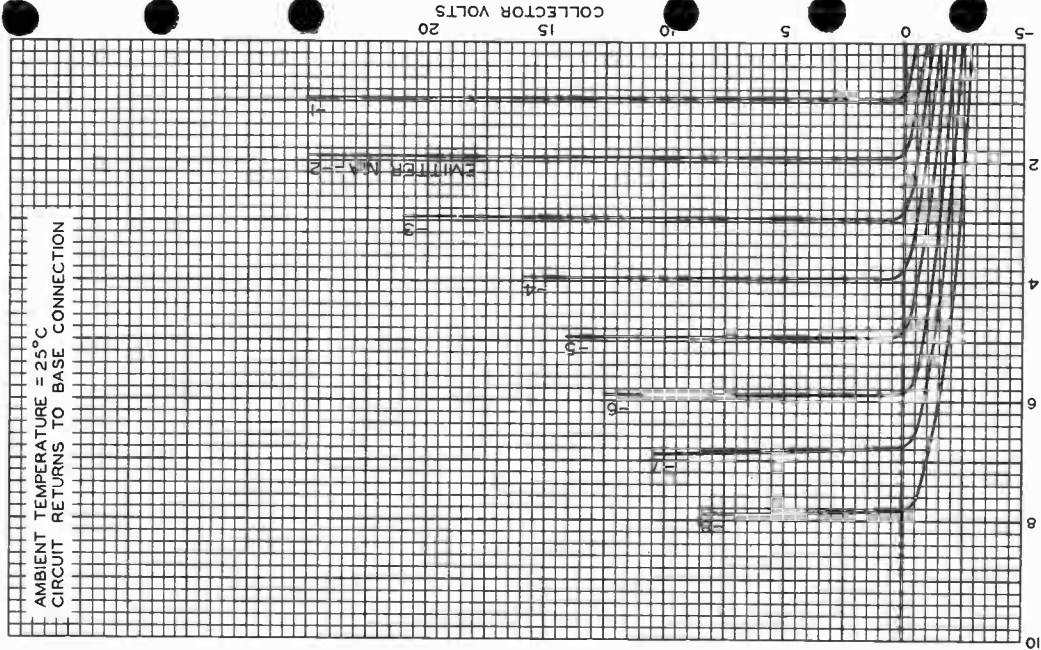
2N35



2N35

# AVERAGE COLLECTOR CHARACTERISTICS

AMBIENT TEMPERATURE = 25°C  
CIRCUIT RETURNS TO BASE CONNECTION



APR. 7, 1953

TUBE DEPARTMENT  
RADIO CORPORATION OF AMERICA, HARRISON, NEW JERSEY

92CM-7960



2N77

## JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For small-signal audio-frequency applications

2N77

## GENERAL DATA

## Electrical:

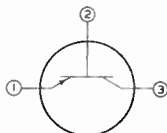
Minimum DC Collector-to-Base Voltage for dc collector current of $-20 \mu\text{amp}$ with emitter open, and at ambient temperature of $25^{\circ}\text{C}$ . . . . .	-30	volts
Maximum DC Collector Current for dc collector-to-base voltage of $-12$ volts with emitter open, and at ambient temperature of $25^{\circ}\text{C}$ . . . . .	-10	$\mu\text{amp}$

## Mechanical:

Mounting Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.405"
Maximum Diameter . . . . .	0.240"
Case . . . . .	Metal, Insulated
Envelope Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Length . . . . .	$1.5" \pm 0.015"$
Orientation and diameter . . . . .	See Dimensional Outline at front of this Section

## BOTTOM VIEW

Lead 1 - Emitter



Lead 2 - Base

Lead 3 - Collector  
(Adjacent  
to red dot  
on side of  
envelope)

## AUDIO-FREQUENCY AMPLIFIER -- Class A

## Maximum Ratings, Absolute Values:

DC COLLECTOR-TO-BASE VOLTAGE . . . . .	-25 max.	volts
DC COLLECTOR CURRENT . . . . .	-15 max.	ma
DC EMITTER CURRENT . . . . .	15 max.	ma
COLLECTOR DISSIPATION . . . . .	35 max.	mw
AMBIENT TEMPERATURE (During operation) . . . . .	50 max.	$^{\circ}\text{C}$
STORAGE-TEMPERATURE RANGE . . . . .	-55 to +70	$^{\circ}\text{C}$

Characteristics, At Ambient Temperature of  $25^{\circ}\text{C}$ :

## Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage . . . . .	-4	volts
DC Collector Current . . . . .	-0.7	ma
Power Gain:		
With load resistance = 0.1 megohm, and input resistance = 1980 ohms . . . . .	44.1	db
With load resistance = 2670 ohms, and input resistance = 2670 ohms . . . . .	34.5	db



## JUNCTION TRANSISTOR

## Noise Factor:

Measured with a noise diode and thermo-couple voltmeter with load resistance = 20,000 ohms, generator resistance = 1000 ohms, and equivalent noise bandwidth = 12.3 kc with geometric mean of 300 cps . . . . .

6.5 db

## Small-Signal T Parameters:\*

DC Collector-to-Emitter Voltage ( $V_{CE}$ ) . . . . .	-4	volts
DC Collector Current ( $I_C$ ) . . . . .	-0.7	ma
Emitter Resistance ( $r_e$ ) . . . . .	23	ohms
Base Resistance ( $r_b$ ) . . . . .	1430	ohms
Mutual Resistance ( $r_m$ ) . . . . .	3.86	megohms
Collector Resistance ( $r_c$ ) . . . . .	3.93	megohms
Current Transfer Ratio ( $\alpha_f$ ) <sup>■</sup> . . . . .	-55	

Small-Signal Hybrid- $\pi$  Parameters:\*

DC Collector-to-Emitter Voltage ( $V_{CE}$ ) . . . . .	-4	volts
DC Collector Current ( $I_C$ ) . . . . .	-0.7	ma
Resistance $r_{bb'}$ . . . . .	240	ohms
Conductance $g_{b'e}$ . . . . .	407	$\mu$ hos
Conductance $g_{ce}$ . . . . .	6.8	$\mu$ hos
Conductance $g_{b'c}$ . . . . .	0.13	$\mu$ ho
Capacitance $C_{b'e}$ . . . . .	5000	$\mu$ ef
Capacitance $C_{b'c}$ . . . . .	40	$\mu$ ef
Intrinsic Transconductance ( $g_m$ ) . . . . .	22300	$\mu$ hos
Frequency <sup>•</sup> for unity power amplification . . . . .	1.7	Mc

## Small-Signal H Parameters:\*

DC Collector-to-Emitter Voltage ( $V_{CE}$ ) . . . . .	-4	volts
DC Collector Current ( $I_C$ ) . . . . .	-0.7	ma
Input Resistance, output circuit shorted ( $h_i$ ) . . . . .	2720	ohms
Reverse Voltage Transfer Ratio, input circuit open ( $h_r$ ) . . . . .	$3.23 \times 10^{-4}$	
Forward Current Transfer Ratio, output circuit shorted ( $h_f$ ) . . . . .	55	
Output Conductance, input circuit open ( $h_o$ ) . . . . .	14	$\mu$ hos

## Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage . . . . .	-4	volts
DC Collector Current . . . . .	-0.7	ma
Power Gain: With load resistance = 0.5 megohm, and input resistance = 215 ohms. . . . .	32.5	db
Frequency at which the current transfer ratio drops to one-half the square root of two times its value at 1 kc. . . . .	700	kc

■ Measured at 1 kc.

\* , •: see next page.





2N77

2N77

# JUNCTION TRANSISTOR

## Common-Collector Circuit, Base Input

DC Emitter-to-Collector Voltage . . . . .	4	volts
DC Emitter Current . . . . .	0.7	ma
Power Gain:		
With load resistance = 10,000 ohms, and input resistance = 0.5 megohm . . . . .	17	db

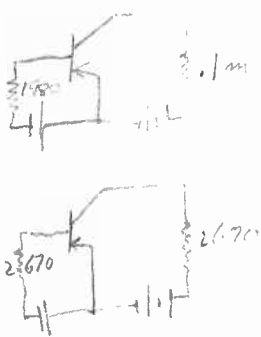
- As derived from corresponding equivalent circuit shown under type 2N104.
- This frequency (figure of merit) may be calculated from the equation

$$f = \frac{1}{4\pi} \sqrt{\frac{g_m}{r_{bb'} \cdot C_{b'e} \cdot C_{b'c}}}$$

### OPERATING CONSIDERATIONS

The 2N77 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The flexible leads of the 2N77 are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.



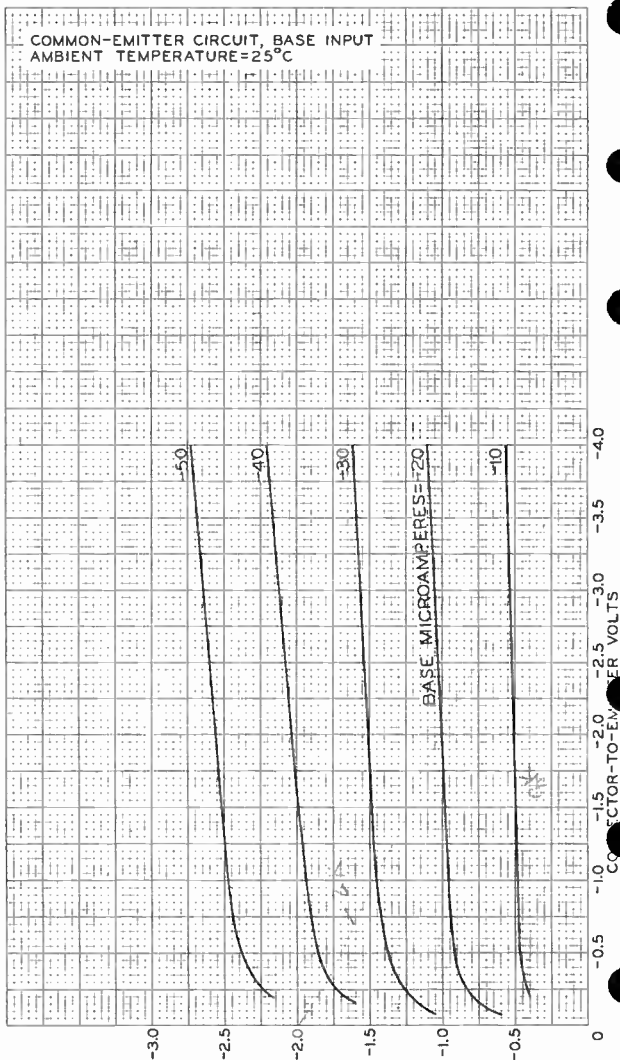
2N77



2N77

# AVERAGE COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE = 25°C



SEMICONDUCTOR DIVISION

RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

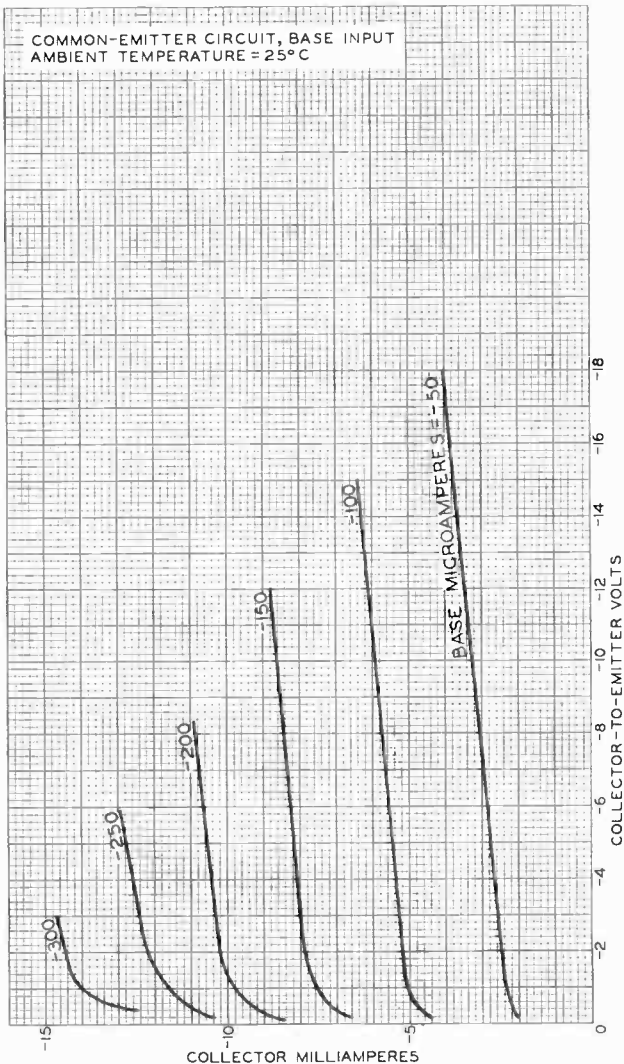
92CM-8589RI



2N77

2N77

# AVERAGE COLLECTOR CHARACTERISTICS

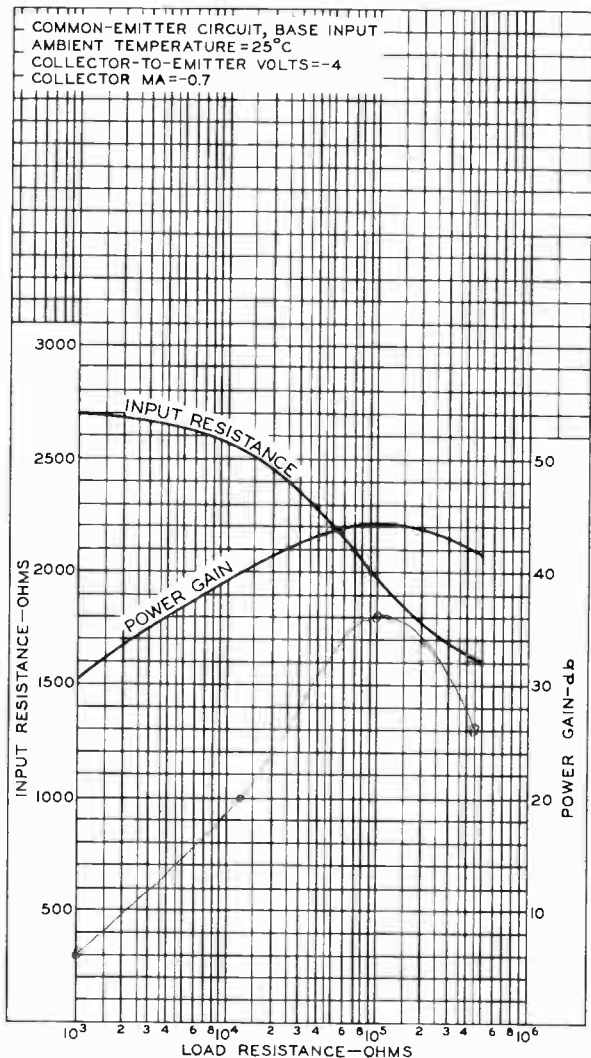


2N77



2N77

## OPERATION CHARACTERISTICS





2N77

2N77

## TYPICAL NOISE CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT

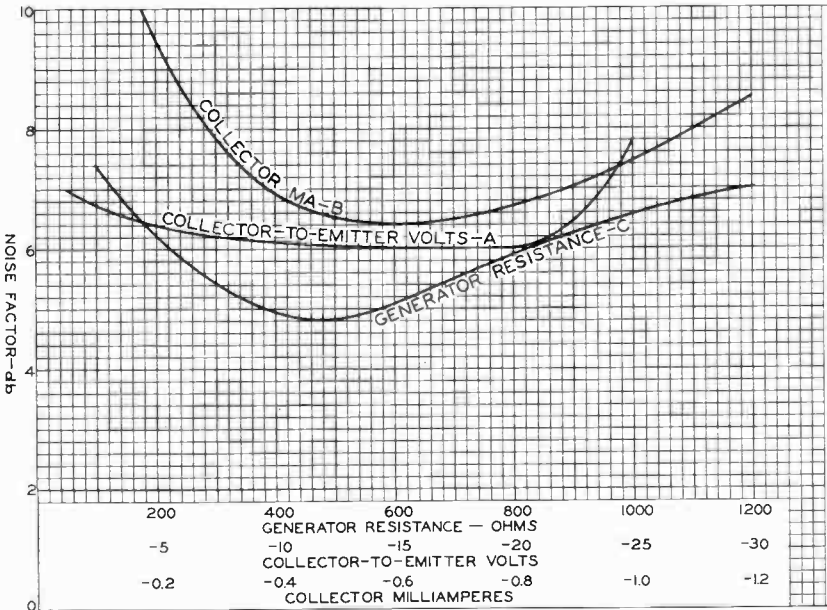
AMBIENT TEMPERATURE = 25°C

MEASURED WITH A NOISE DIODE AND THERMOCOUPLE VOLT-

METER WITH LOAD RESISTANCE = 20000 OHMS AND EQUIVALENT

NOISE BANDWIDTH = 12.3 KC WITH GEOMETRIC MEAN OF 300 CPS

CURVE	GENERATOR RESISTANCE (OHMS)	COLLECTOR-TO-EMITTER VOLTS	COLLECTOR MA
A	1000	—	-0.7
B	1000	-4	—
C	—	-4	-0.7

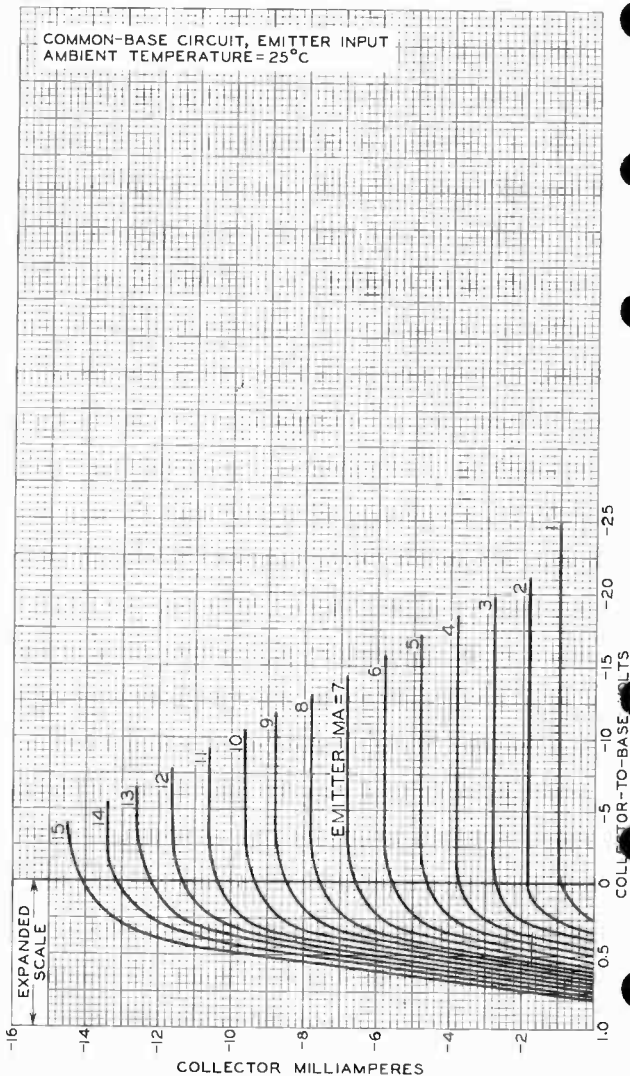


2N77



2N77

## AVERAGE COLLECTOR CHARACTERISTICS

COMMON-BASE CIRCUIT, EMITTER INPUT  
AMBIENT TEMPERATURE = 25°CSEMICONDUCTOR DIVISION  
RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

92CM-8587RI

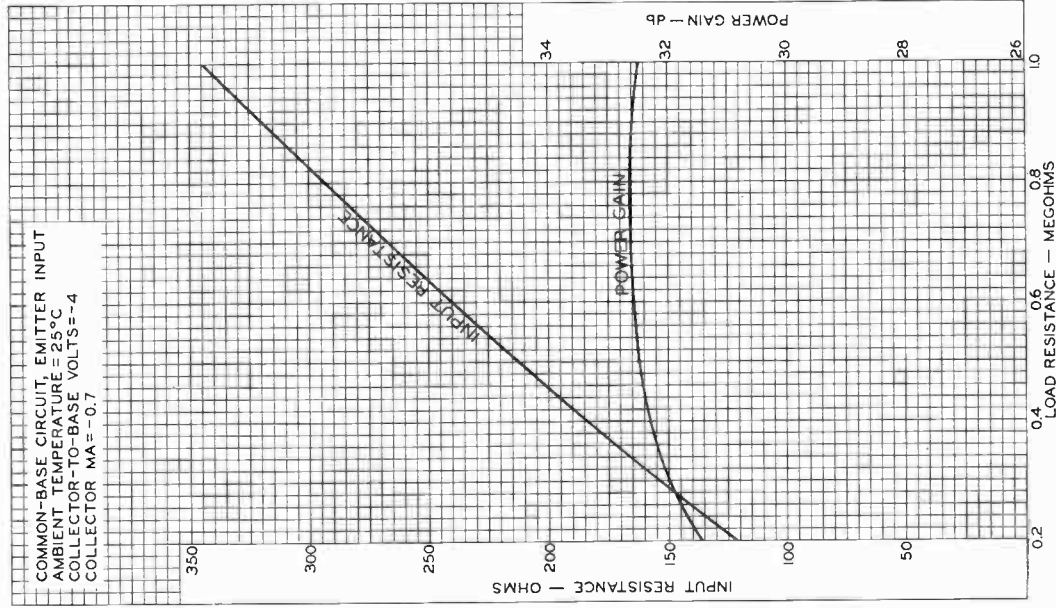


2N77

2N77

# OPERATION CHARACTERISTICS

COMMON-BASE CIRCUIT, EMITTER INPUT  
AMBIENT TEMPERATURE = 25°C  
COLLECTOR-TO-BASE VOLTS = -4  
COLLECTOR MA = -0.7

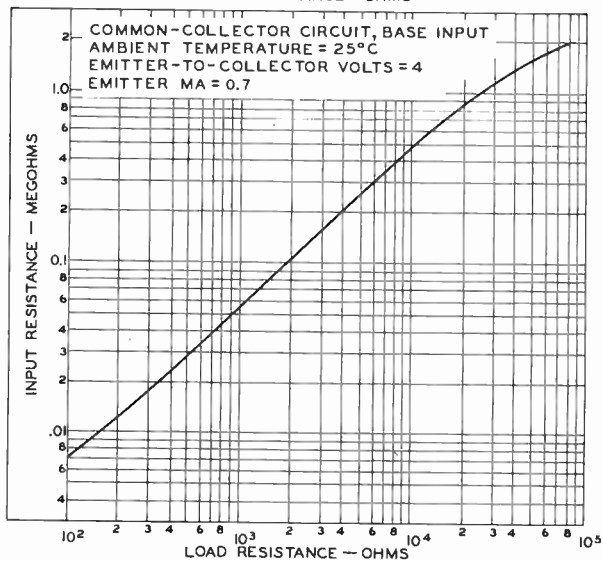
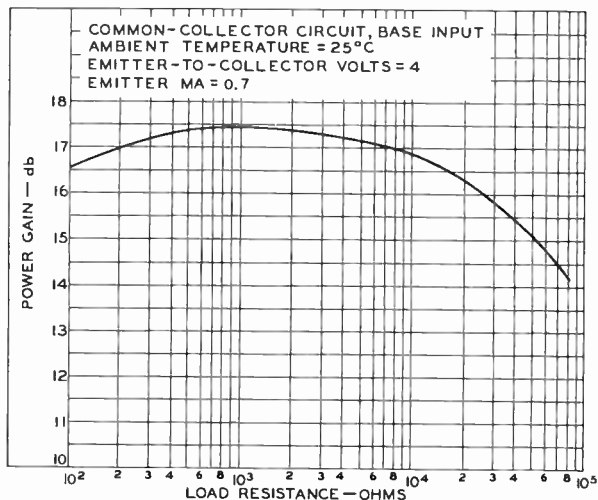


2N77



2N77

## OPERATION CHARACTERISTICS







2N104

2N104

## JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For small-signal audio-frequency applications

## GENERAL DATA

## Electrical:

Minimum DC Collector-to-Base Voltage for dc collector current of $-20 \mu\text{amp}$ with emitter open, and at ambient temperature of $25^{\circ}\text{C}$ . . . . .	$-30$	volts
Maximum DC Collector Current for dc collector-to-base voltage of $-12$ volts with emitter open, and at ambient temperature of $25^{\circ}\text{C}$ . . . . .	$-10$	$\mu\text{amp}$
Maximum DC Emitter Current for dc emitter-to-base voltage of $-12$ volts with collector open, and at ambient temperature of $25^{\circ}\text{C}$ . . . . .	$-10$	$\mu\text{amp}$
Junction Temperature Rise (in free air) . . . . .	$0.4$	$^{\circ}\text{C}/\text{mw}$

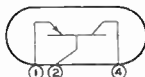
## Mechanical:

Mounting Position . . . . .	Any
Maximum Overall Length . . . . .	$0.697''$
Maximum Seated Length . . . . .	$0.495''$
Maximum Diameter . . . . .	$0.260''$
Dimensional Outline . . . . .	See front of this Section
Case . . . . .	Metal, Insulated
Envelope Seals . . . . .	Hermetic
Base . . . . .	Small-Round Linotetraz 3-Pin (JETEC No. E3-25)

Pin 1 - Emitter

Pin 4 - Collector

Pin 2 - Base



## AUDIO-FREQUENCY AMPLIFIER -- Class A

## Maximum Ratings, Absolute Values:

DC COLLECTOR-TO-BASE VOLTAGE . . . . .	$-30$ max.	volts
DC COLLECTOR CURRENT . . . . .	$-50$ max.	ma
DC EMITTER CURRENT . . . . .	$50$ max.	ma
TRANSISTOR DISSIPATION . . . . .	See Rating Chart	
AMBIENT TEMPERATURE (During operation) . . . . .	$70$ max.	$^{\circ}\text{C}$
STORAGE-TEMPERATURE RANGE . . . . .	$-55$ to $+85$	$^{\circ}\text{C}$

Characteristics, At Ambient Temperature of  $25^{\circ}\text{C}$ :

## Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage . . . . .	$-4$	$-6$	volts
DC Collector Current . . . . .	$-0.7$	$-1$	ma
Power Gain:			
With load resistance = $20,000$ ohms, and input resistance = $1400$ ohms. . . . .	$-$	$41$	db



2N104

## JUNCTION TRANSISTOR

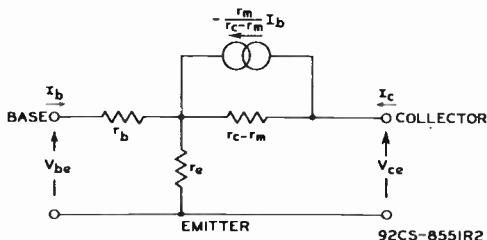
## Noise Factor:

Measured with a noise diode and thermocouple voltmeter with load resistance = 20,000 ohms, generator resistance = 518 ohms, and equivalent noise bandwidth = 12.3 kc with geometric mean of 300 cps . . . . .

6.5 - db

Small-Signal  $T$  Parameters:

Derived from the accompanying one-generator equivalent circuit, and applicable to that portion of the audio-frequency range in which internal capacitance effects may be neglected

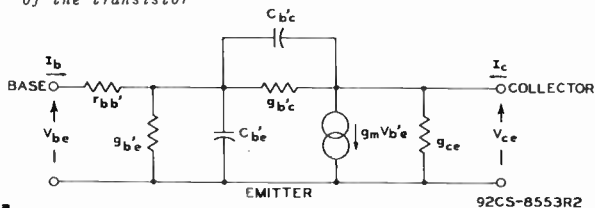


For conditions where  $-r_m / (r_c - r_m) \cong -(r_m + r_e) / (r_c - r_m + r_e) = \alpha_f$ :

DC Collector-to-Emitter Voltage ( $V_{CE}$ ) . . . . .	-3	-6	volts
DC Collector Current ( $I_C$ ) . . . . .	-0.2	-1	ma
Emitter Resistance ( $r_e$ ) . . . . .	155	21.7	ohms
Base Resistance ( $r_b$ ) . . . . .	960	690	ohms
Mutual Resistance ( $r_m$ ) . . . . .	2.86	1.93	megohms
Collector Resistance ( $r_c$ ) . . . . .	2.95	1.974	megohms
Current Transfer Ratio ( $\alpha_f$ ) <sup>a</sup> . . . . .	-32	-44	

Small-Signal Hybrid- $\pi$  Parameters:

Derived from the accompanying one-generator equivalent circuit, and applicable over the useful frequency range of the transistor



<sup>a</sup> Measured at 1 kc.



2N104

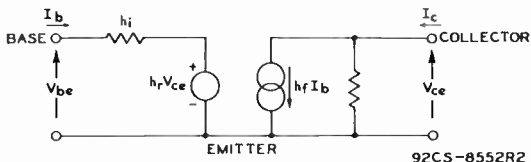
2N104

## JUNCTION TRANSISTOR

DC Collector-to-Emitter Voltage ( $V_{CE}$ )	-3	-6	volts
DC Collector Current ( $I_C$ )	-0.2	-1	ma
Resistance $r_{bb'}$	300	290	ohms
Conductance $g_{b'e}$	174	727	$\mu$ mhos
Conductance $g_{ce}$	1.28	6.62	$\mu$ mhos
Conductance $g_{b'c}$	0.3	0.36	$\mu$ mho
Capacitance $C_{b'e}$	1225	6900	$\mu$ mf
Capacitance $C_{b'c}$	36	40	$\mu$ mf
Intrinsic Transconductance ( $g_m$ )	5540	32000	$\mu$ mhos
Frequency for unity power amplification	1.6	1.6	Mc

## Small-Signal H Parameters:

Derived from accompanying two-generator equivalent circuit, and applicable to that portion of the audio-frequency range in which internal capacitance effects may be neglected



DC Collector-to-Emitter Voltage ( $V_{CE}$ )	-3	-6	volts
DC Collector Current ( $I_C$ )	-0.2	-1	ma
Input Resistance, output circuit shorted ( $h_i$ )	6040	1667	ohms
Reverse Voltage Transfer Ratio, input circuit open ( $h_r$ )	$17.2 \times 10^{-4}$	$4.95 \times 10^{-4}$	
Forward Current Transfer Ratio, output circuit shorted ( $h_f$ )	32	44	
Output Conductance, input circuit open ( $h_o$ )	11.1	22.8	$\mu$ mhos

## Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage	-3	-6	volts
DC Collector Current	-0.2	-1	ma
Power Gain:			
With load resistance = 0.5 megohm, and input resistance = 170 ohms.	-	32.4	db
Frequency at which the current transfer ratio drops to one-half the square root of two times its value at 1 kc	530	700	kc

\*: See next page.



2N104

## JUNCTION TRANSISTOR

## Common-Collector Circuit, Base Input

DC Emitter-to-Collector Voltage. . . . .	3	volts
DC Emitter Current . . . . .	0.2	ma
Power Gain:		
With load resistance = 18,000 ohms,		
and input resistance = 0.5 megohm. . . . .	14.3	db

- This frequency (figure of merit) may be calculated from the equation

$$f = \frac{1}{4\pi} \sqrt{\frac{g_m}{r_{bb'} \cdot C_{b'e} \cdot C_{b'c}}}$$

## OPERATING CONSIDERATIONS

The 2N104 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

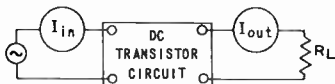
## TRANSISTOR DISSIPATION RATING CHART

The Transistor Dissipation Rating Chart may be used to determine, for a particular circuit application, the maximum allowable transistor dissipation. On this chart, solid boundary lines ABC, DEF, and GHI are the loci of the maximum allowable dissipation for operating ambient temperatures of 25°C, 50°C, and 70°C, respectively. The dashed curves for the various values of circuit stability factor represent conditions where the maximum allowable dissipation is current limited by the maximum dc collector current rating of 50 milliamperes.

It is recommended that the 50°C-ambient-temperature curve be used in commercial applications, and the 70°C curve for industrial applications. The 25°C curve should not be used unless the equipment is operated under closely controlled ambient-temperature conditions.

To use this chart it is only necessary to know the dc collector-to-emitter voltage, dc collector current, ambient temperature after equipment warm-up, and the circuit stability factor,  $S_F$ .

The circuit stability factor is equal to the dc-circuit current gain of the transistor (between collector and base) plus one. It may be measured empirically from the arrangement shown at left. If a current,  $I_{in}$ , of 1 microampere dc is passed through the transistor circuit, the value of  $I_{out}$  in microamperes measured plus one is equal to the circuit stability factor.



where  $I_{in}$  = input current  
 $I_{out}$  = output current  
 and  $R_L$  = load resistance



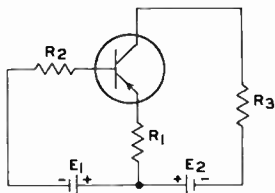
2N104

2N104

## JUNCTION TRANSISTOR

For conditions where the base spreading resistance,  $r_{bb1}$ , is much less than the external emitter- or base-circuit resistance, and where the forward current transfer ratio,  $\alpha_f$ , is much greater than 1, the circuit stability factor may also be calculated for three commonly-used dc circuit configurations from the formulas below:

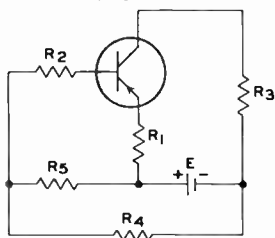
CIRCUIT A



$$S_F = \frac{|\alpha_f|(R_1 + R_2)}{R_2 + |\alpha_f|R_1}$$

Two-battery-operated stage

CIRCUIT B

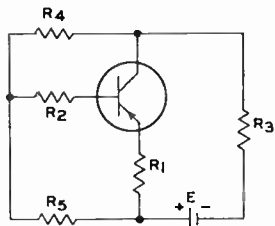


$$S_F = \frac{|\alpha_f|(R_1 + R_{eq})}{R_{eq} + |\alpha_f|R_1}$$

$$\text{where } R_{eq} = R_2 + \frac{R_4 R_5}{R_4 + R_5}$$

Single-battery-operated stage

CIRCUIT C



$$S_F = \frac{|\alpha_f|(P + Q)}{Q + |\alpha_f|P}$$

where

$$P = R_1(R_3 + R_4 + R_5) + R_3 R_5$$

$$Q = R_2(R_3 + R_4 + R_5) + R_4 R_5$$

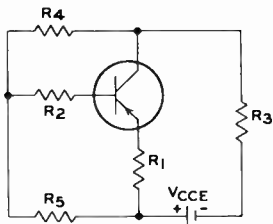
Single-battery-operated stage  
with degenerative feedback



2N104

## JUNCTION TRANSISTOR

For example, in the following dc equivalent circuit for a typical commercial application employing common-emitter circuit, base input, it is desired to determine if the transistor will be operating within dissipation rating if the dc collector-to-emitter voltage is -6 volts, the dc collector current is -1 milliampere, and the ambient temperature after equipment warm-up is 50°C. Under these conditions, the transistor dissipation is approximately equal to the collector dissipation  $V_{CE} \times I_C$ , or 6 milliwatts.



Circuit components:

$R_1$	= 270 ohms
$R_2$	= 1000 ohms
$R_3$	= 9000 ohms
$R_4$	= 43000 ohms
$R_5$	= 3900 ohms

(1) By use of the curve showing the variation of the forward current transfer ratio,  $\alpha_f$ , with ambient temperature, for an ambient temperature of 50°C, a value of  $\alpha_f$  equal to -56 is obtained.

(2) Using formulas shown for circuit C,

$$P = 270(9000 + 43000 + 3900) + (9000)(3900)$$

$$P = 5.02 \times 10^7 \text{ ohms}^2$$

$$Q = 1000(9000 + 43000 + 3900) + (43000)(3900)$$

$$Q = 22.4 \times 10^7 \text{ ohms}^2$$

$$S_F = \frac{56 [(5.02 \times 10^7) + (22.4 \times 10^7)]}{(22.4 \times 10^7) + 56 (5.02 \times 10^7)}$$

$$S_F = 5.06$$

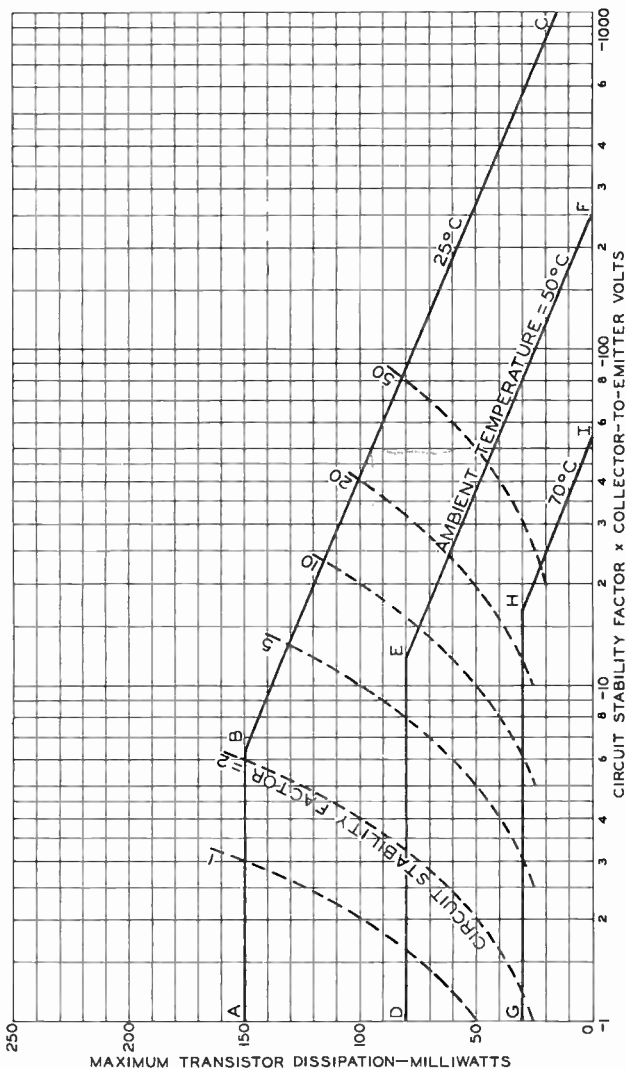
(3) Referring to the dissipation chart, for an abscissa ( $S_F \times V_{CE} = 5.06 \times -6$ ) of -30.4 and an ambient temperature of 50°C, the maximum dissipation rating is 55 milliwatts. Since the actual transistor dissipation of 6 milliwatts is well within the maximum dissipation, the transistor is being operated with a considerable degree of safety.



2N104

2N104

# TRANSISTOR DISSIPATION RATING CHART



MAXIMUM TRANSISTOR DISSIPATION—MILLIWATTS

SEMICONDUCTOR DIVISION

92CM-8530R1

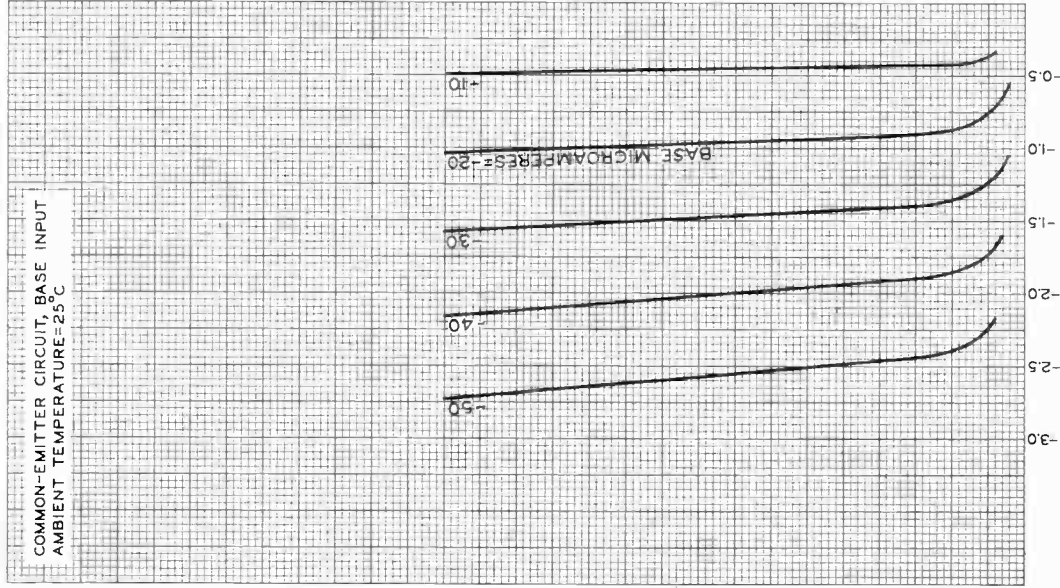
RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY



2N104

# AVERAGE COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE=25°C



COLLECTOR MILLIAMPERES

SEMICONDUCTOR DIVISION

RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

92CM-8524R1

2N104



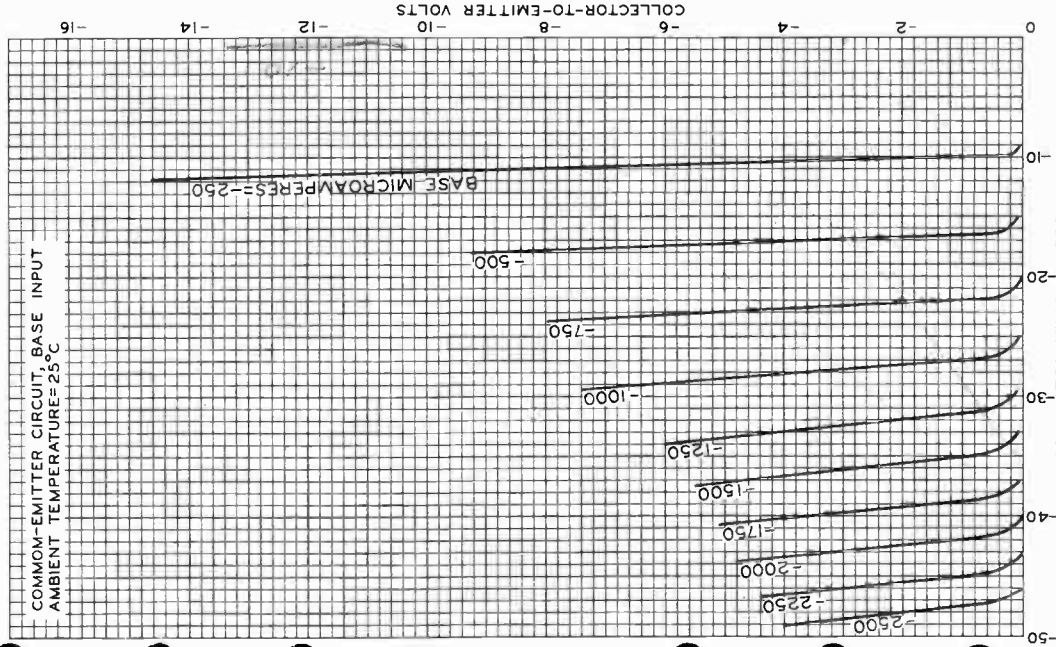


2N104

2N104

# AVERAGE COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE = 25°C



SEMICONDUCTOR DIVISION

RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

92CM-8512R1

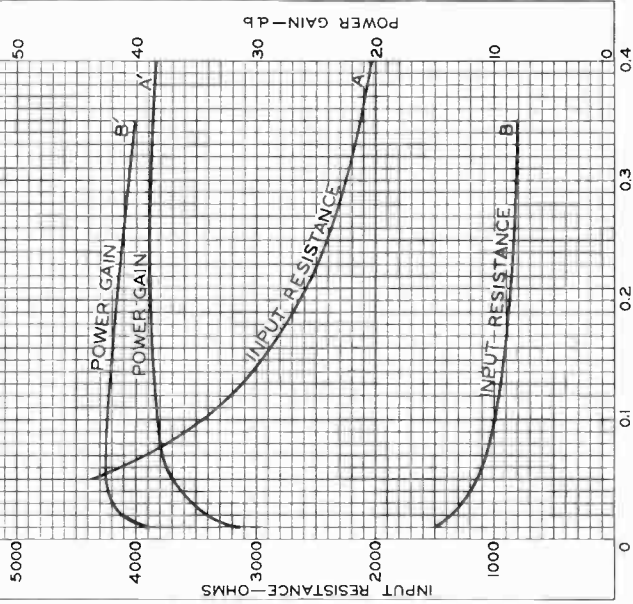


2N104

## OPERATION CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
 AMBIENT TEMPERATURE = 25°C

CURVE	COLLECTOR-TO-EMITTER VOLTS	COLLECTOR MA
A & A'	-3	-0.2
B & B'	-6	-1



LOAD RESISTANCE — MEGOHMS

SEMICONDUCTOR DIVISION

RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

92CM-8518R2



2N104

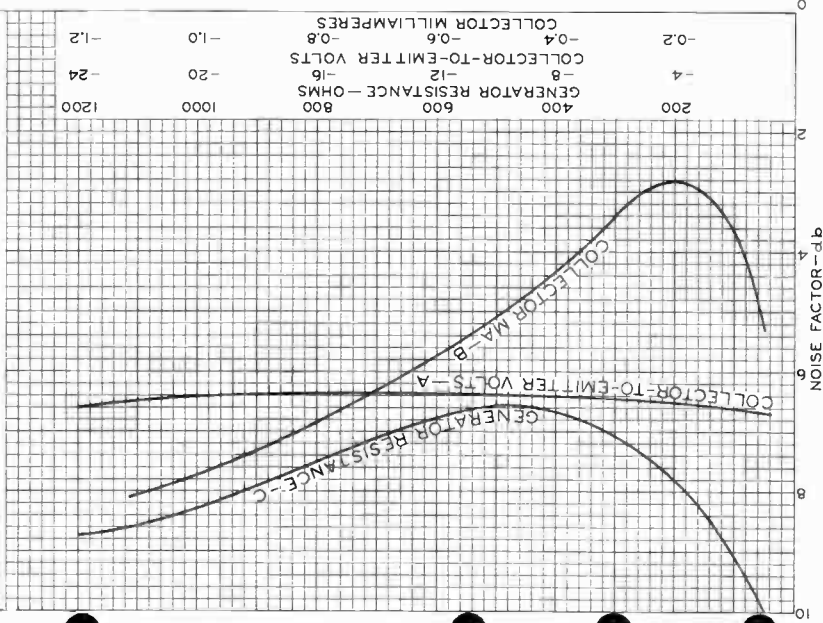
2N104

## TYPICAL NOISE CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
 AMBIENT TEMPERATURE = 25°C

MEASURED WITH A NOISE DIODE AND THERMOCOUPLE VOLT-  
 METER WITH LOAD RESISTANCE=20000 OHMS AND EQUIVALENT  
 NOISE BANDWIDTH=12.3KC WITH GEOMETRIC MEAN OF 300CPS

CURVE	GENERATOR RESISTANCE (OHMS)	COLLECTOR-TO-EMITTER VOLTS	COLLECTOR MA
A	518	—	-0.7
B	518	-4	—
C	—	-4	-0.7



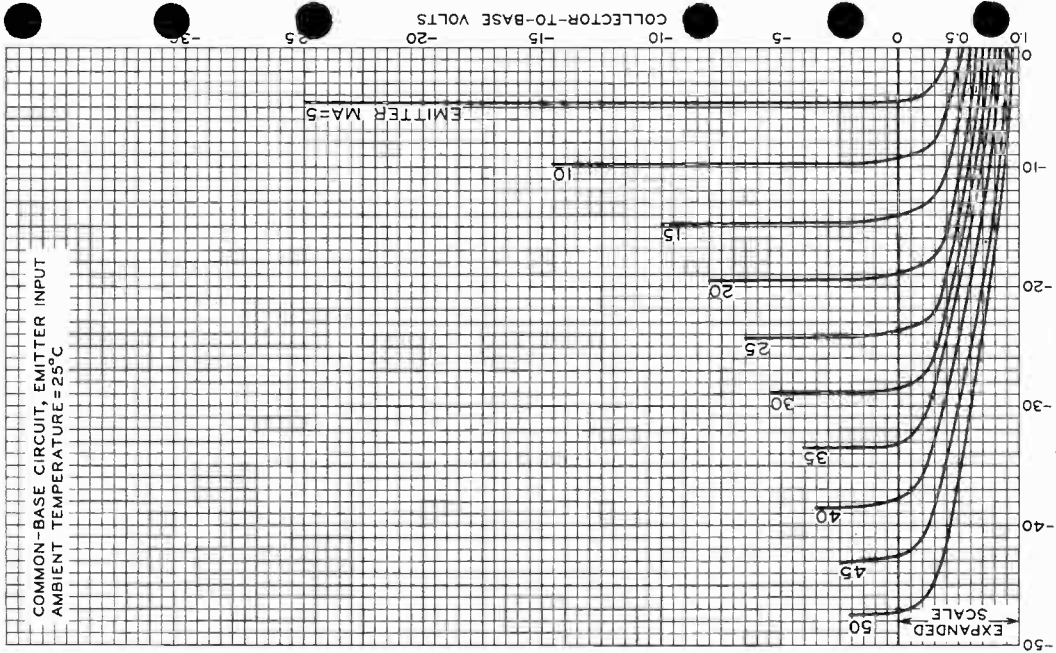
2N104



2N104

# AVERAGE COLLECTOR CHARACTERISTICS

COMMON-BASE CIRCUIT, EMITTER INPUT  
AMBIENT TEMPERATURE = 25°C



92CM-8515R1  
SEMICONDUCTOR DIVISION  
RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

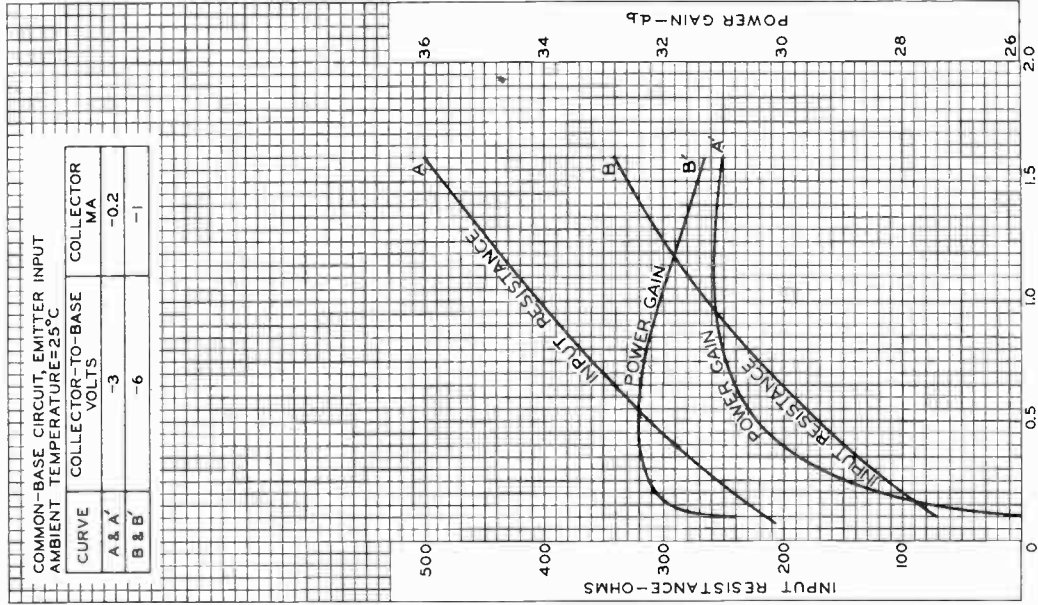


2N104

## OPERATION CHARACTERISTICS

COMMON-BASE CIRCUIT, EMITTER INPUT  
AMBIENT TEMPERATURE=25°C

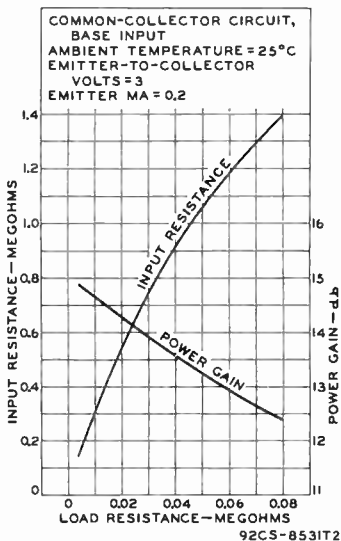
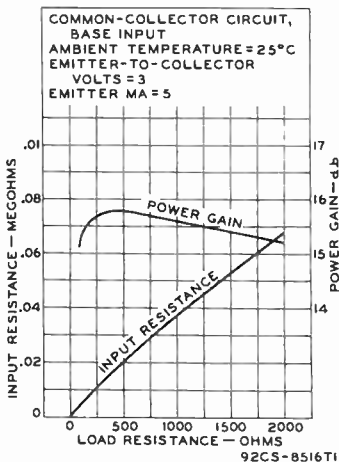
CURVE	COLLECTOR-TO-BASE VOLTS	COLLECTOR MA
A & A'	-3	-0.2
B & B'	-6	-1





2N104

## OPERATION CHARACTERISTICS

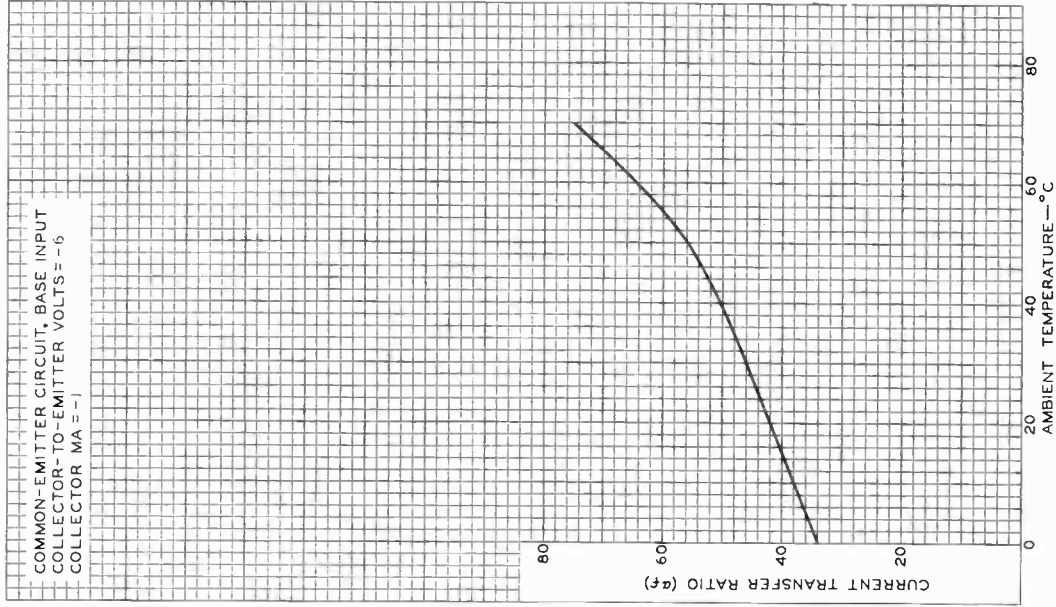




2N104

2N104

### AVERAGE CHARACTERISTIC

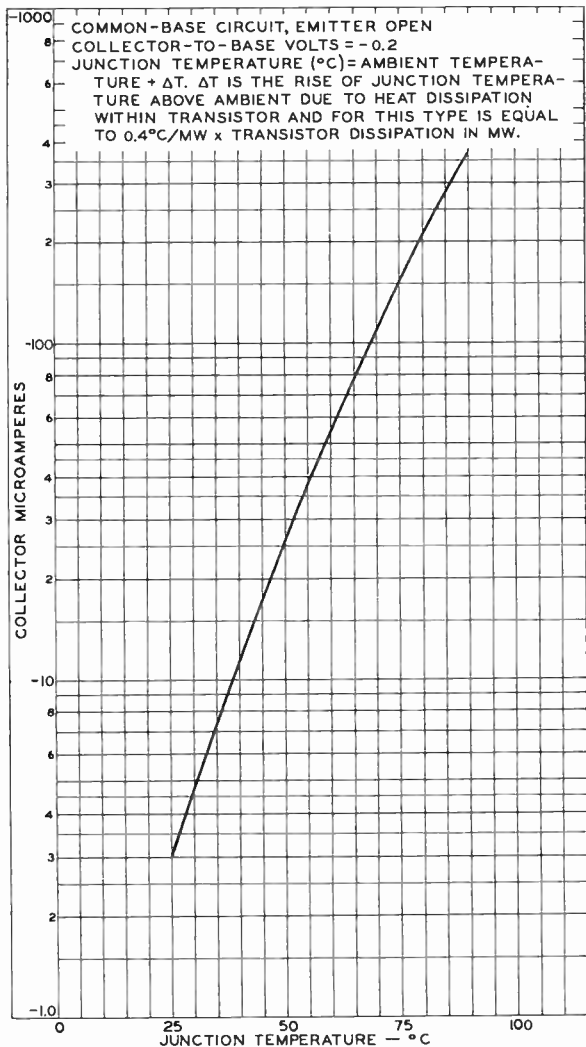


2N104



2N104

### OPERATION CHARACTERISTIC







2N105

2N105

## JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For small-signal audio-frequency applications

## GENERAL DATA

## Electrical:

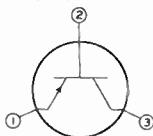
Minimum DC Collector-to-Base Voltage for dc collector current of $-10 \mu\text{amp}$ with emitter open, and at ambient temperature of $25^{\circ}\text{C}$ . . . . .	-35	volts
Maximum DC Collector Current for dc collector-to-base voltage of $-12$ volts with collector open, and at ambient temperature of $25^{\circ}\text{C}$ . . . . .	-5	$\mu\text{amp}$

## Mechanical:

Mounting Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.255"
Maximum Diameter . . . . .	0.135"
Case . . . . .	Metal, Insulated
Envelope Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Length . . . . .	$1.5" \pm 0.015"$
Orientation and diameter . . . . .	See Dimensional Outline at front of this Section

## BOTTOM VIEW

Lead 1 - Emitter

Lead 3 - Collector  
(Red band)

Lead 2 - Base

## AUDIO-FREQUENCY AMPLIFIER -- Class A

## Maximum Ratings, Absolute Values:

DC COLLECTOR-TO-BASE VOLTAGE . . . . .	-25 max.	volts
DC COLLECTOR CURRENT . . . . .	-15 max.	ma
DC EMITTER CURRENT . . . . .	15 max.	ma
COLLECTOR DISSIPATION . . . . .	35 max.	mw
AMBIENT TEMPERATURE (During operation) . . . . .	50 max.	$^{\circ}\text{C}$
STORAGE-TEMPERATURE RANGE . . . . .	-55 to +70	$^{\circ}\text{C}$

Characteristics, At Ambient Temperature of  $25^{\circ}\text{C}$ :

## Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage . . . . .	-1.3	-4	volts
DC Collector Current . . . . .	-0.3	-0.7	ma
Power Gain:			
With load resistance = 4700 ohms, and input resistance = 4700 ohms . . . . .	32.5	-	db
With load resistance = 20,000 ohms, and input resistance = 2300 ohms . . . . .	-	42	db



2N105

## JUNCTION TRANSISTOR

## Noise Factor:

Measured with a noise diode and thermocouple voltmeter with load resistance = 20,000 ohms, generator resistance = 1000 ohms, and equivalent noise bandwidth = 12.3 kc with geometric mean of 300 cps

Maximum value. . . . .	16.5	-	db
Typical value. . . . .	7.5	-	db

## Small-Signal T Parameters:\*

DC Collector-to-Emitter Voltage ( $V_{CE}$ ) . . . . .	-1.3	-4	volts
DC Collector Current ( $I_C$ ) . . . . .	-0.3	-0.7	ma
Emitter Resistance ( $r_e$ ) . . . . .	73	34	ohms
Base Resistance ( $r_b$ ) . . . . .	1400	976	ohms
Mutual Resistance ( $r_m$ ) . . . . .	3.66	3.39	megohms
Collector Resistance ( $r_c$ ) . . . . .	3.74	3.45	megohms
Current Transfer Ratio ( $\alpha_f$ ) <sup>■</sup> . . . . .	-45	-55	

Small-Signal Hybrid- $\pi$  Parameters:\*

DC Collector-to-Emitter Voltage ( $V_{CE}$ ) . . . . .	-1.3	-4	volts
DC Collector Current ( $I_C$ ) . . . . .	-0.3	-0.7	ma
Resistance $r_{bb'}$ . . . . .	260	250	ohms
Conductance $g_{b'e}$ . . . . .	220	380	$\mu$ hos
Conductance $g_{ce}$ . . . . .	3.1	4.5	$\mu$ hos
Conductance $g_{b'c}$ . . . . .	0.20	0.21	$\mu$ ho
Capacitance $C_{b'e}$ . . . . .	2500	4500	$\mu$ f
Capacitance $C_{b'c}$ . . . . .	27	17	$\mu$ f
Intrinsic Transconductance ( $g_m$ ) . . . . .	10000	21000	$\mu$ hos
Frequency* for unity power amplification. . . . .	1.9	2.6	Mc

## Small-Signal H Parameters:\*

DC Collector-to-Emitter Voltage ( $V_{CE}$ ) . . . . .	-1.3	-4	volts
DC Collector Current ( $I_C$ ) . . . . .	-0.3	-0.7	ma
Input Resistance, output circuit shorted ( $h_i$ ) . . . . .	4800	2880	ohms
Reverse Voltage Transfer Ratio, input circuit open ( $h_r$ ) . . . . .	$9.1 \times 10^{-4}$	$5.5 \times 10^{-4}$	
Forward Current Transfer Ratio, output circuit shorted ( $h_f$ ) . . . . .	45	55	
Output Conductance, input circuit open ( $h_o$ ) . . . . .	12.4	16.3	$\mu$ hos

\* As derived from corresponding equivalent circuit shown under type 2N104.

■ Measured at 1 kc.

• See next page.



2N105

2N105

## JUNCTION TRANSISTOR

*Common-Base Circuit, Emitter Input*

DC Collector-to-Base Voltage. . . . .	-4	volts
DC Collector Current. . . . .	-0.7	ma
Power Gain:		
With load resistance = 0.5 megohm, and input resistance = 180 ohms . . . . .	33.2	db
Frequency at which the current transfer ratio drops to one-half the square root of two times its value at 1 kc . . . . .	700	kc

*Common-Collector Circuit, Base Input*

DC Emitter-to-Collector Voltage . . . . .	1.3	volts
DC Emitter Current. . . . .	0.3	ma
Power Gain:		
With load resistance = 13,000 ohms, and input resistance = 0.5 megohm . . . . .	16	db

- This frequency (figure of merit) may be calculated from the equation

$$f = \frac{1}{4\pi} \sqrt{\frac{g_m}{r_{bb'} C_{b'c} C_{c'e}}}$$

## OPERATING CONSIDERATIONS

The 2N105 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of the 2N105 are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

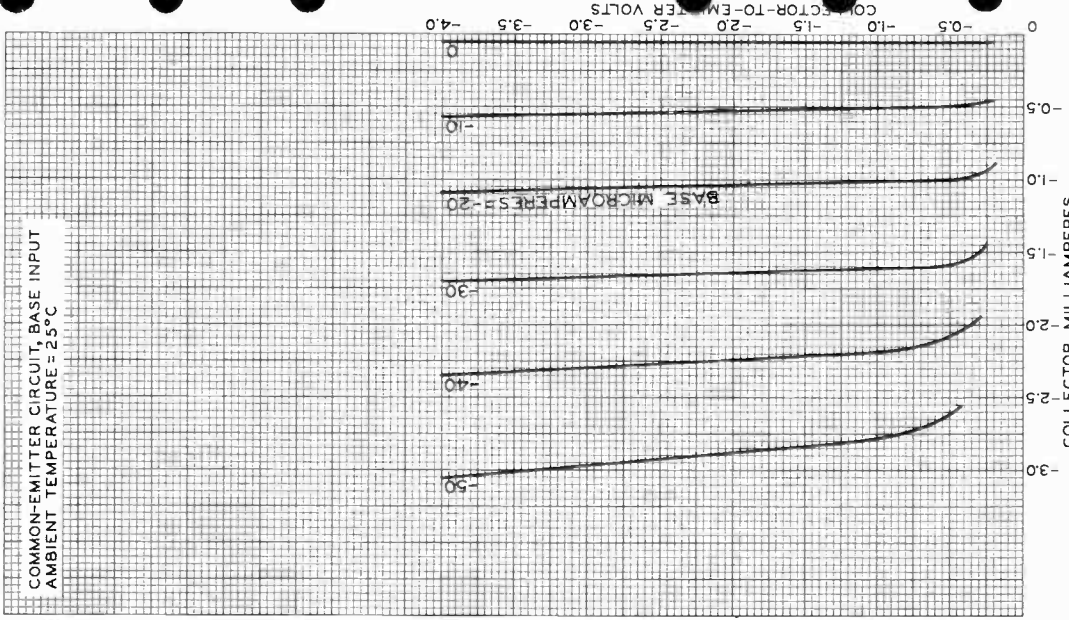
2N105



2N105

# AVERAGE COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE = 25°C



COLLECTOR MILLIAMPERES  
SEMICONDUCTOR DIVISION  
RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY  
92CM-8571R1

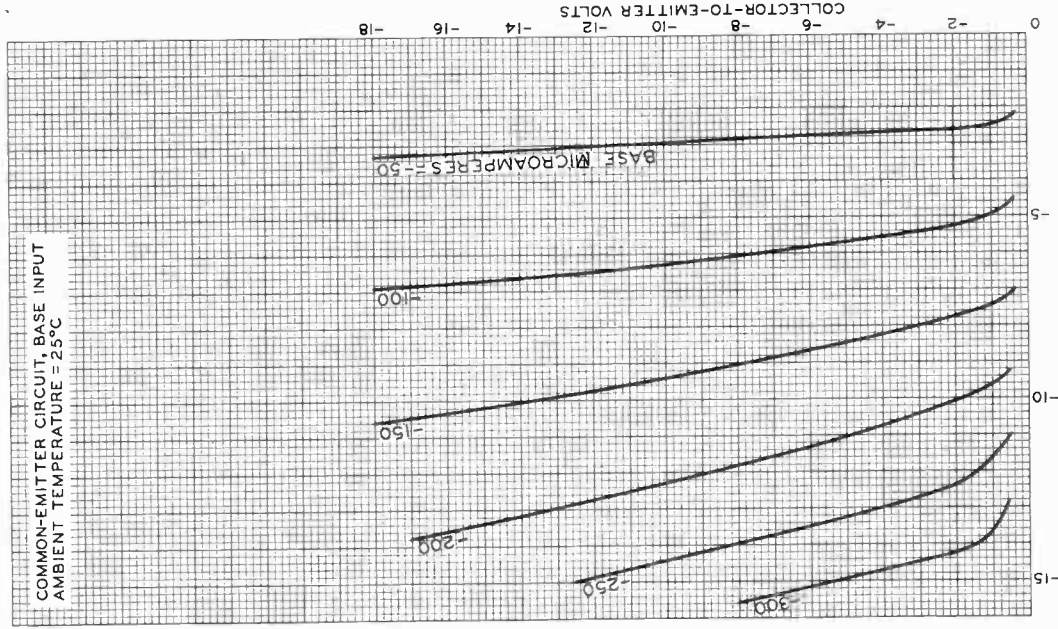


2N105

2N105

# AVERAGE COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE = 25°C



COLLECTOR MILLIAMPERES

SEMICONDUCTOR DIVISION

RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

92CM-8572RI

2N105

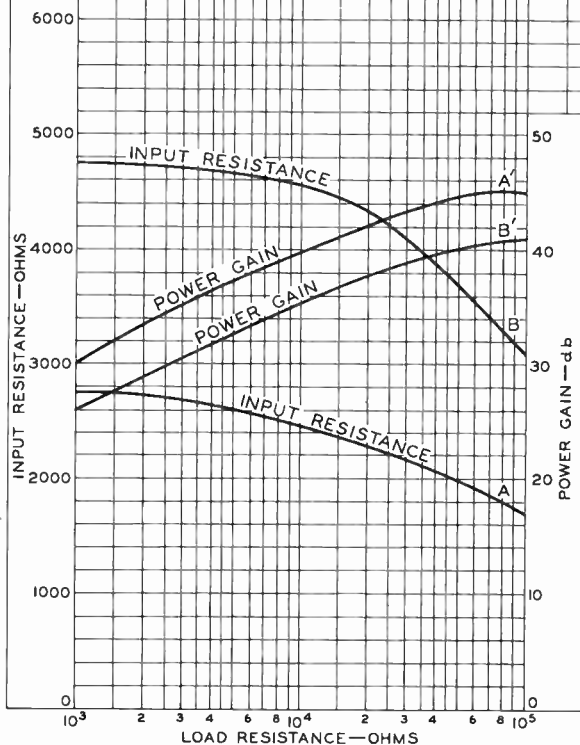


2N105

## OPERATION CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
 AMBIENT TEMPERATURE = 25°C

CURVE	COLLECTOR-TO-EMITTER VOLTS	COLLECTOR MA
A & A'	-4	-0.7
B & B'	-1.3	-0.3





2N105

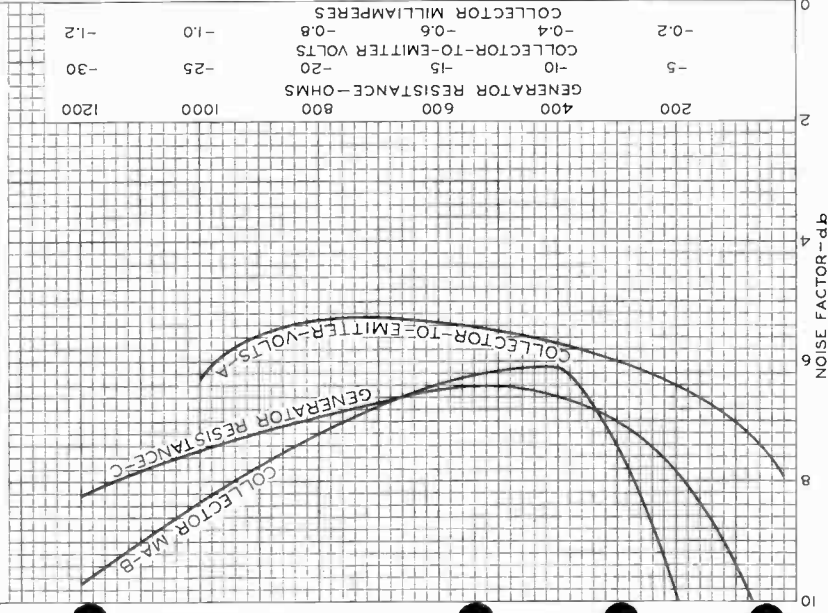
2N105

# TYPICAL NOISE CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE=25°C

MEASURED WITH A NOISE DIODE AND THERMOCOUPLE VOLT-METER WITH LOAD RESISTANCE=20000 OHMS AND EQUIVALENT NOISE BANDWIDTH=12.3 KC WITH GEOMETRIC MEAN OF 300 CPS

CURVE	GENERATOR RESISTANCE (OHMS)	COLLECTOR-TO-EMITTER VOLTS	COLLECTOR MA
A	1000	—	-0.3
B	1000	-1.3	—
C	—	-1.3	-0.3



92CM-858IRI

SEMICONDUCTOR DIVISION  
RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

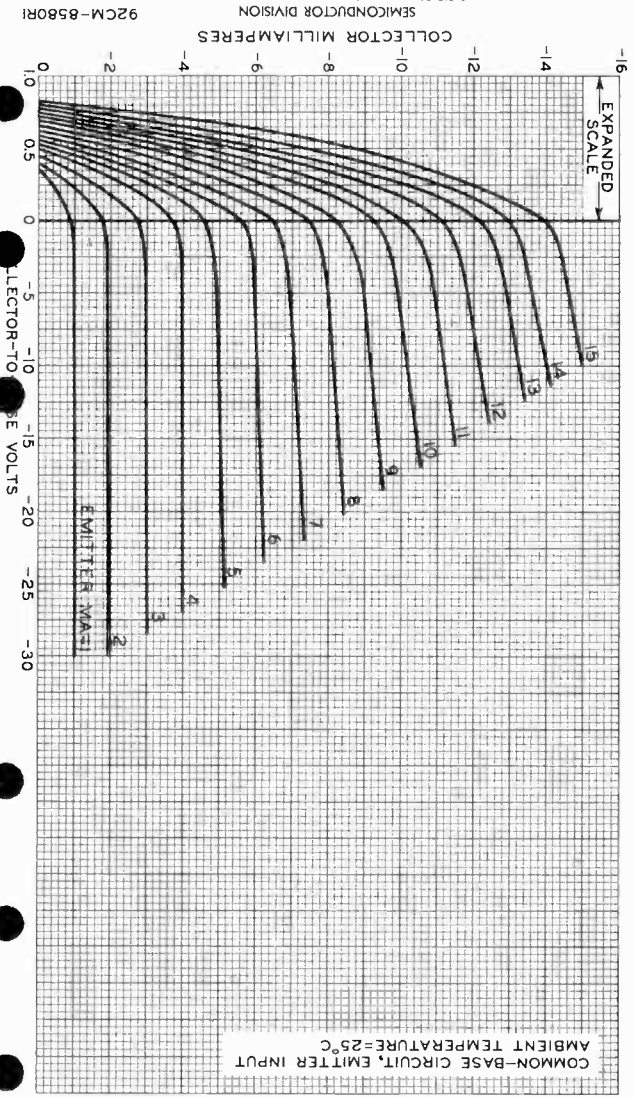
2N105



2N105

# AVERAGE COLLECTOR CHARACTERISTICS

COMMON-BASE CIRCUIT, EMITTER INPUT  
AMBIENT TEMPERATURE = 25°C



92CM-8580R1

SEMICONDUCTOR DIVISION  
RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY



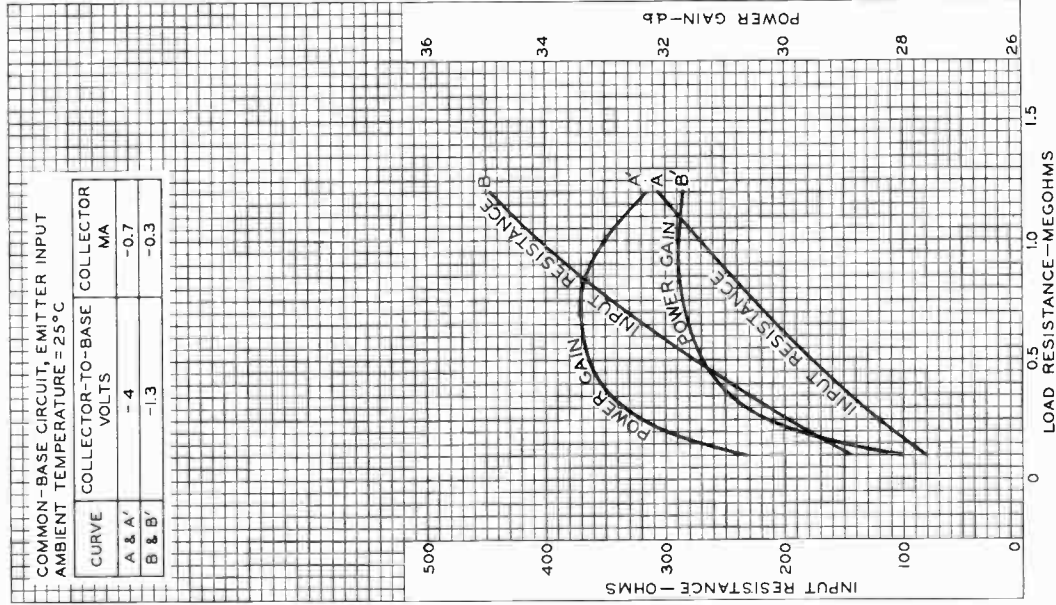


2N105

## OPERATION CHARACTERISTICS

COMMON-BASE CIRCUIT, EMITTER INPUT  
AMBIENT TEMPERATURE = 25°C

CURVE	COLLECTOR-TO-BASE VOLTS	COLLECTOR MA
A & A'	-4	-0.7
B & B'	-1.3	-0.3



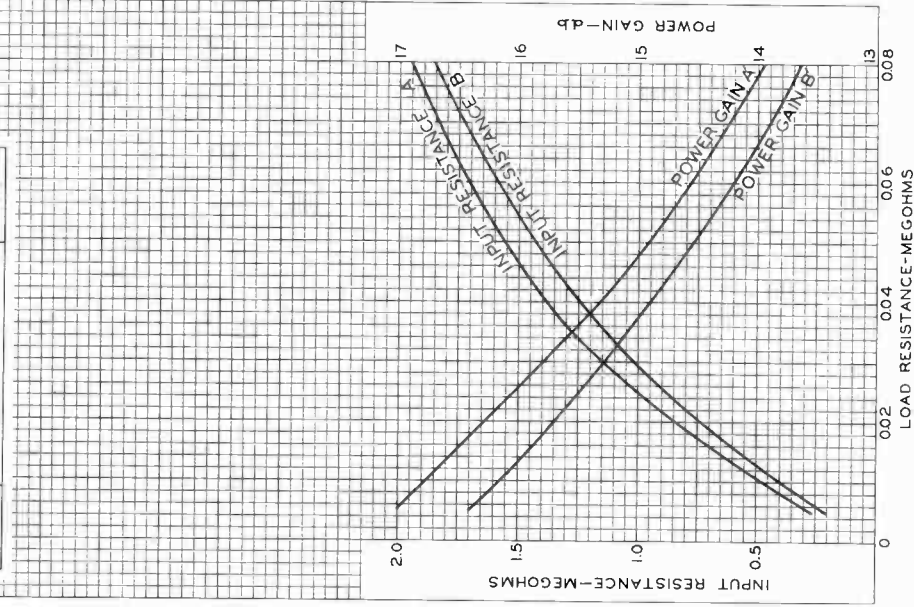


2N105

## OPERATION CHARACTERISTICS

COMMON-COLLECTOR CIRCUIT, BASE INPUT  
 AMBIENT TEMPERATURE=25°C

CURVE	EMITTER-TO-COLLECTOR VOLTS	EMITTER MA
A & A'	4	0.7
B & B'	1.3	0.3



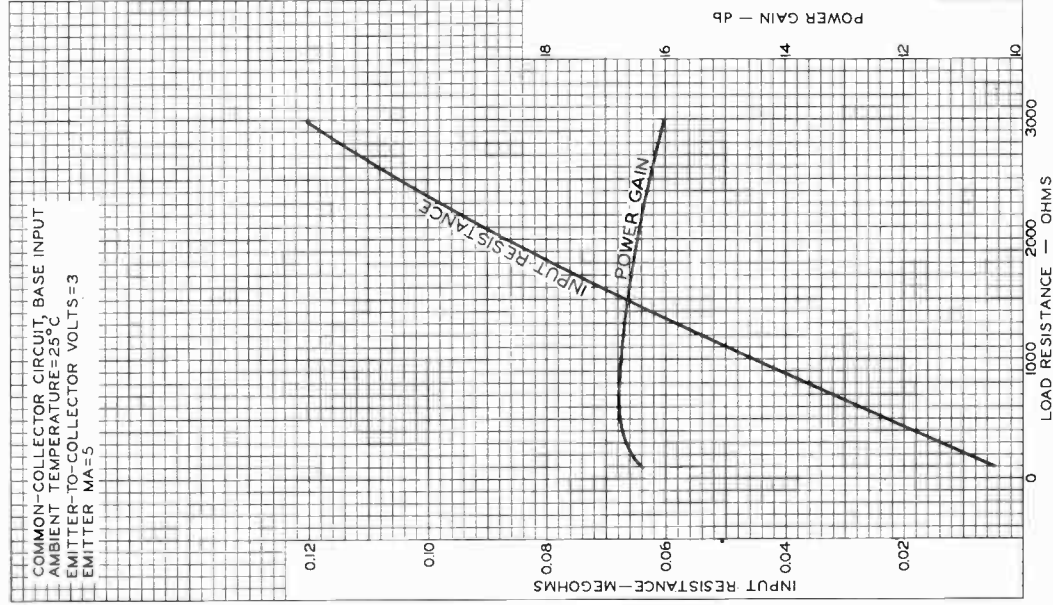


2N105

2N105

# OPERATION CHARACTERISTICS

COMMON-COLLECTOR CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE = 25°C  
EMITTER-TO-COLLECTOR VOLTS = 3  
EMITTER MA = 5







2N109

2N109

# JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For large-signal audio-frequency applications

## GENERAL DATA

### Electrical:

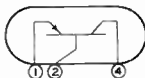
Maximum DC Collector Current for dc collector-to-base voltage of -25 volts with emitter open, and at ambient temperature of 25°C. . . . .	-10	μamp
Maximum DC Emitter Current for dc emitter-to-base voltage of -25 volts with collector open, and at ambient temperature of 25°C. . . . .	-10	μamp

### Mechanical:

Mounting Position. . . . .	Any
Maximum Overall Length. . . . .	0.697"
Maximum Seated Length. . . . .	0.495"
Maximum Diameter. . . . .	0.260"
Dimensional Outline. . . . .	See front of this Section
Case. . . . .	Metal, Insulated
Envelope Seals. . . . .	Hermetic
Base. . . . .	Small-Round Linotetrar 3-Pin (JETEC No. E3-25)

Pin 1 - Emitter

Pin 2 - Base



Pin 4 - Collector

## AUDIO-FREQUENCY AMPLIFIER -- Class B

### Maximum Ratings, Absolute Values:

PEAK COLLECTOR-TO-BASE VOLTAGE . . . . .	-25 max.	volts
DC COLLECTOR-TO-BASE VOLTAGE (For inductive load). . . . .	-12 max.	volts
PEAK COLLECTOR CURRENT . . . . .	-70 max.	ma
AVERAGE COLLECTOR CURRENT. . . . .	-35 max.	ma
PEAK EMITTER CURRENT . . . . .	70 max.	ma
AVERAGE EMITTER CURRENT. . . . .	35 max.	ma
COLLECTOR DISSIPATION. . . . .	50 max.	mw
AMBIENT TEMPERATURE (During operation) . . . . .	50 max.	°C
STORAGE-TEMPERATURE RANGE. . . . .	-55 to +85	°C

### Characteristics, At Ambient Temperature of 25°C:

Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage. . . . .	-1	volt
DC Collector Current . . . . .	-50	ma
Large-Signal DC Current Transfer Ratio . . . . .	70	

2N109



2N109

## JUNCTION TRANSISTOR

Typical Push-Pull Operation, At Ambient Temperature of 25°C:

Common-Emitter Circuit, Base Input

Unless otherwise specified, values are for 2 transistors

DC Collector-to-Emitter Supply Voltage . . . . .	-4.5	-9	volts
DC Base-to-Emitter Voltage . . . . .	-0.15	-0.15	volt
Peak Collector Current (Per transistor). . . . .	-35	-40	ma
Zero-Signal DC Collector Current (Per transistor). . . . .	-2	-2	ma
Max.-Signal DC Collector Current (Per transistor). . . . .	-11.5	-13	ma
Signal-Source Impedance (Base to base) . . . . .	1500	1500	ohms
Load Impedance (Collector to collector) . . . . .	400	800	ohms
Signal Frequency . . . . .	1	1	kc
Circuit Efficiency . . . . .	60	69	%
Power Gain . . . . .	30	33	db
Total Harmonic Distortion. . . . .	7	7	%
Max.-Signal Power Output . . . . .	75	160	mw

### OPERATING CONSIDERATIONS

The 2N109 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

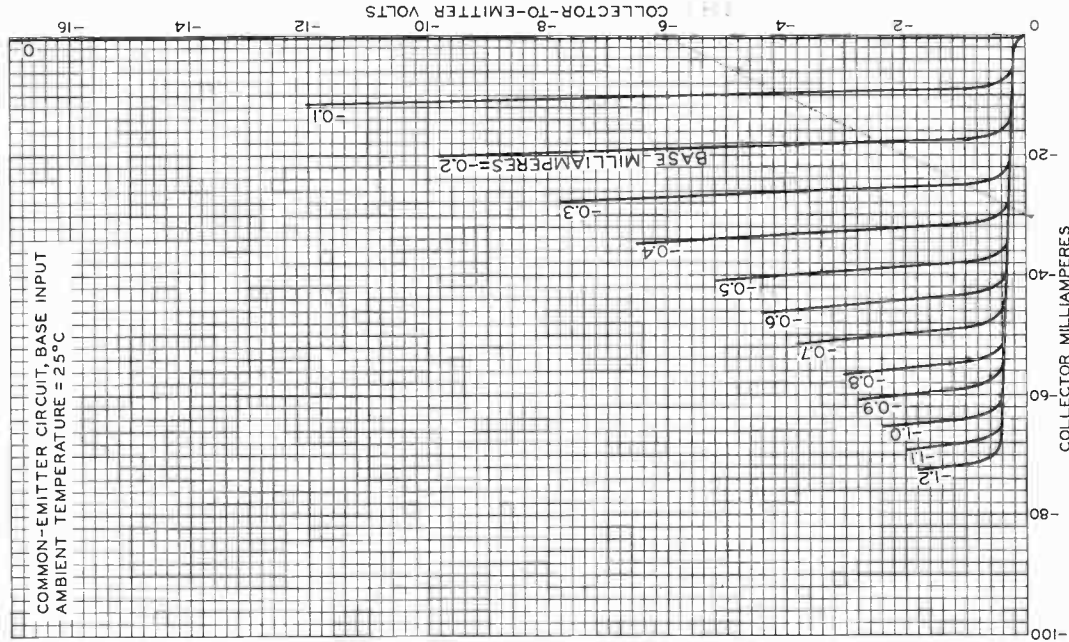
In class B service, when the 2N109 is operated at ambient temperatures other than 25°C, the base-to-emitter voltage should be reduced or increased by approximately 0.002 volt for each degree the ambient temperature is above or below 25°C, respectively. When this transistor is operated under varying ambient temperatures, some form of temperature compensation may be used in the base-to-emitter circuit to hold the operating point constant.



2N109

# AVERAGE COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE = 25°C



2N109

COLLECTOR MILLIAMPERES

SEMICONDUCTOR DIVISION

RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

92CM-8599R2

COLLECTOR-TO-EMITTER VOLTS

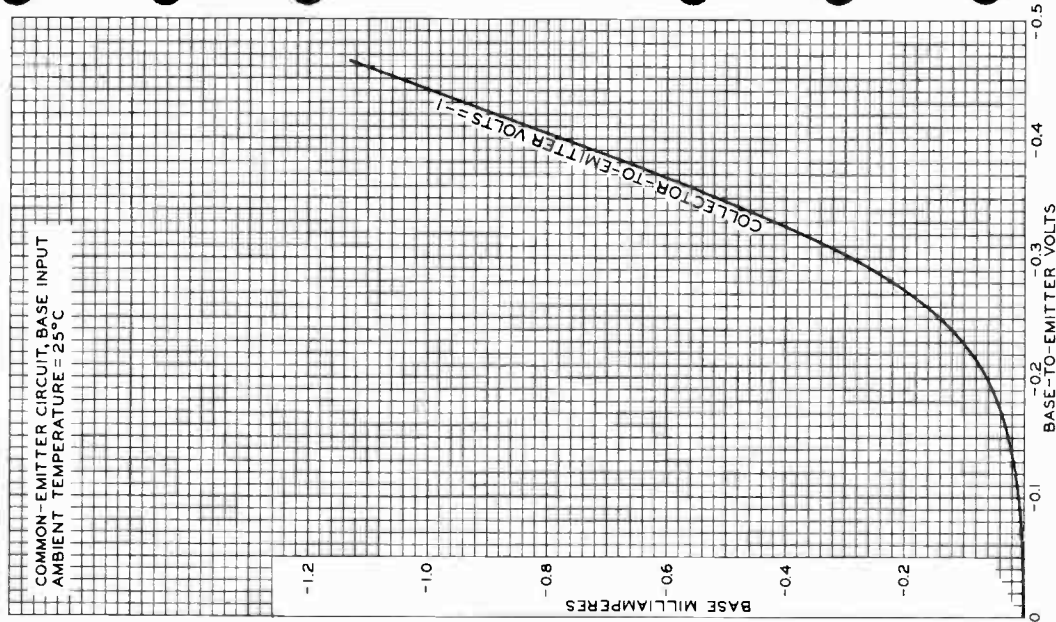


2N109

2N109

# AVERAGE BASE CHARACTERISTIC

COMMON-EMITTER CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE = 25°C



COLLECTOR-TO-EMITTER VOLTS = -1

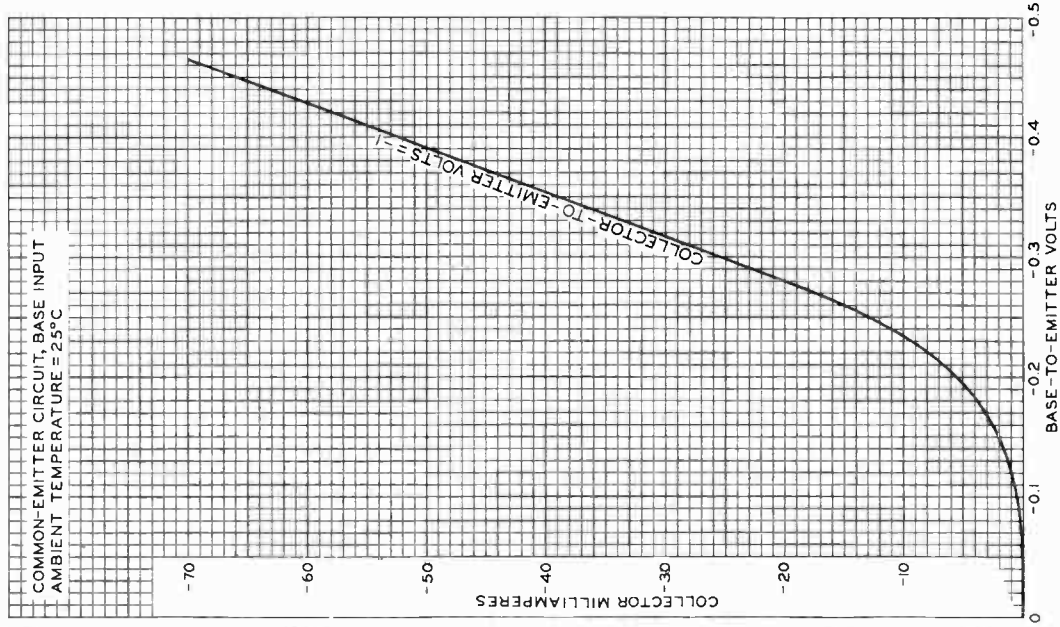




2N109

2N109

### AVERAGE CHARACTERISTIC



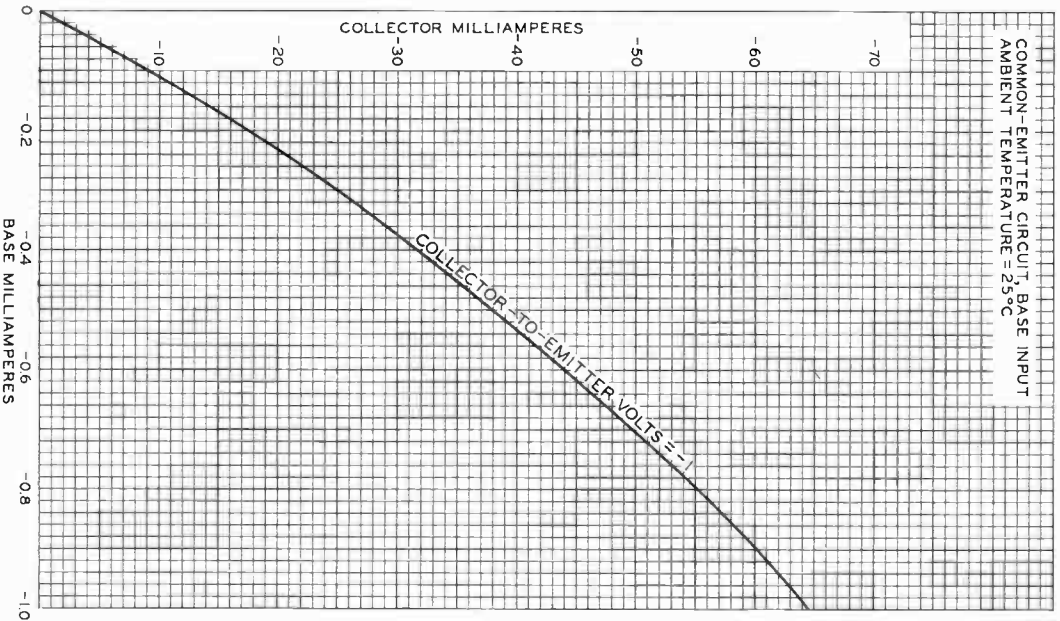
2N109



2N109

### AVERAGE CHARACTERISTIC

COMMON-EMITTER CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE = 25°C





2N139

2N139

## JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For 455-*kc* Intermediate-frequency applications

## GENERAL DATA

## Electrical:

Minimum DC Collector-to-Base Voltage for dc collector current of $-10 \mu\text{amp}$ with emitter open, and at ambient temperature of $25^{\circ}\text{C}$ . . . . .	-16	volts
Maximum DC Collector Current for dc collector-to-base voltage of $-12$ volts with emitter open, and at ambient temperature of $25^{\circ}\text{C}$ . . . . .	-6	$\mu\text{amp}$
Maximum DC Emitter Current for dc emitter-to-base voltage of $-12$ volts with collector open, and at ambient temperature of $25^{\circ}\text{C}$ . . . . .	-40	$\mu\text{amp}$

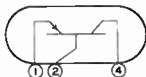
## Mechanical:

Mounting Position . . . . .	Any
Maximum Overall Length . . . . .	0.697"
Maximum Seated Length . . . . .	0.495"
Maximum Diameter . . . . .	0.260"
Dimensional Outline . . . . .	See front of this Section
Case . . . . .	Metal, Insulated
Envelope Seals . . . . .	Hermetic
Base . . . . .	Small-Round Linotetraz 3-Pin (JETEC No. E3-25)

Pin 1 - Emitter

Pin 4 - Collector

Pin 2 - Base



## INTERMEDIATE-FREQUENCY AMPLIFIER SERVICE

## Maximum Ratings, Absolute Values:

DC COLLECTOR-TO-BASE VOLTAGE . . . . .	-16 max.	volts
DC EMITTER-TO-BASE VOLTAGE . . . . .	-12 max.	volts
DC COLLECTOR CURRENT . . . . .	-15 max.	ma
DC EMITTER CURRENT . . . . .	15 max.	ma
COLLECTOR DISSIPATION . . . . .	35 max.	mw
AMBIENT TEMPERATURE (During operation) . . . . .	70 max.	$^{\circ}\text{C}$
STORAGE-TEMPERATURE RANGE . . . . .	-55 to +85	$^{\circ}\text{C}$

Characteristics, At Ambient Temperature of  $25^{\circ}\text{C}$ :

## Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage . . . . .	-9	-9	volts
DC Collector Current . . . . .	-0.5	-1	ma
Current Transfer Ratio ( $\alpha_f$ ) . . . . .	-45	-48	

■: See next page.



2N139

## JUNCTION TRANSISTOR

Small-Signal Hybrid- $\pi$  Parameters:\*

DC Collector-to-Emitter Voltage ( $V_{CE}$ ).	-9	-9	volts
DC Collector Current ( $I_C$ ).	-0.5	-1	ma
Resistance $r_{bb'}$ .	85	75	ohms
Conductance $g_{b'e}$ .	425	800	$\mu$ mhos
Conductance $g_{ce}$ .	4.6	8.6	$\mu$ mhos
Conductance $g_{b'c}$ .	0.22	0.25	$\mu$ mho
Capacitance $C_{b'e}$ .	900	1550	$\mu$ mf
Capacitance $C_{b'c}$ .	9.5	9.5	$\mu$ mf
Intrinsic Transconductance ( $g_m$ ).	19300	38600	$\mu$ mhos
Frequency* for unity power amplification.	13	14	Mc

## Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage . . . . .	-9	-9	volts
DC Collector Current . . . . .	-0.5	-1	ma
Current Transfer Ratio <sup>†</sup> . . . . .	0.978	0.980	
Frequency at which the current trans- fer ratio drops to one-half the square root of two times its value at 1 kc.	4.5	4.7	Mc

## Typical Operation, At Ambient Temperature of 25°C:

## Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage. . . . .	-9	-9	volts
DC Collector Current . . . . .	-0.5	-1	ma
Input Resistance . . . . .	1000	500	ohms
Output Resistance. . . . .	70000	30000	ohms
Spot Noise Factor <sup>‡</sup> . . . . .	4.5	4.5	db
Maximum Power Gain <sup>‡</sup> . . . . .	38	37	db
Useful Power Gain. . . . .	27.6 <sup>§</sup>	30.4 <sup>†</sup>	db

\* As derived from corresponding equivalent circuit shown under type 2N104.

• This frequency (figure of merit) may be calculated from the equation

$$f = \frac{1}{4\pi} \sqrt{\frac{g_m}{r_{bb'} C_{b'c} C_{b'e}}}$$

■ Measured at 1 kc.

▲ Measured in a single-tuned unilateralized circuit matched to the generator and load impedances for maximum transfer of power. Transformer insertion losses not included. (Unilateralization is a special case of neutralization in which the resistive as well as the reactive feedback parameters are balanced out. Unilateralization changes a bilateral network into a unilateral network).

§ A transformer insertion loss of 10.4 db is included in this figure.

† A transformer insertion loss of 6.6 db is included in the figure.

## OPERATING CONSIDERATIONS

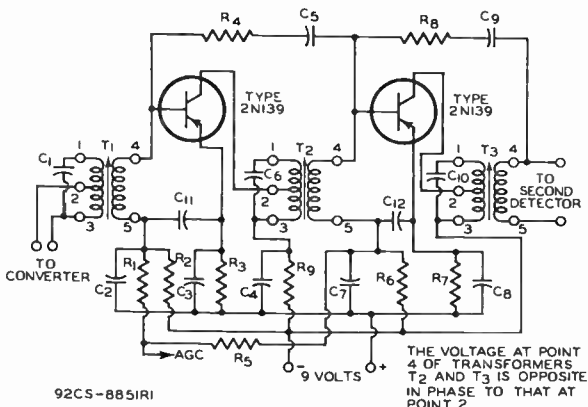
The 2N139 should not be connected into or disconnected from circuits with the power are because high transient currents may cause permanent damage to the transistor.



2N139

2N139

## JUNCTION TRANSISTOR

TYPICAL 455-KC INTERMEDIATE-FREQUENCY  
AMPLIFIER CIRCUIT

C1 C6 C10: 220  $\mu\text{f}$   
 C2: 50  $\mu\text{f}$   
 C3 C4 C8: 0.05  $\mu\text{f}$   
 C5: 75  $\mu\text{f}$   
 C7: 25  $\mu\text{f}$   
 C9: 33  $\mu\text{f}$   
 C11 C12: 0.1  $\mu\text{f}$   
 R1: 12400 ohms

R2: 0.15 megohm  
 R3 R7: 820 ohms  
 R4: 560 ohms  
 R5: 18000 ohms  
 R6: 0.1 megohm  
 R8: 2000 ohms  
 R9: 560 ohms

## Transformer:

	T1	T2	T3	
Reflected resistance of primary between terminals 2 and 3 with secondary terminated. . . . .	206000	29000	10900	ohms
Reflected resistance of secondary with primary terminated. . . . .	1000	500	1000	ohms
Turns ratios:				
Terminals 1 and 3 to terminals 2 and 3. . . . .	1.17	2.48	3.16	
Terminals 1 and 3 to terminals 4 and 5. . . . .	16.8	18.9	10.43	
Terminals 2 and 3 to terminals 4 and 5. . . . .	14.35	7.62	3.3	
Core Material. . . . .	Ferrite	Ferrite	Ferrite	
Unloaded Q (mounted in chassis). . . . .	110	61	110	
Loaded Q (mounted in chassis). . . . .	35	35	35	

Devices and arrangements shown or described herein may use patents of RCA or others. Information contained herein is furnished without responsibility by RCA for its use and without prejudice to RCA's patent rights.

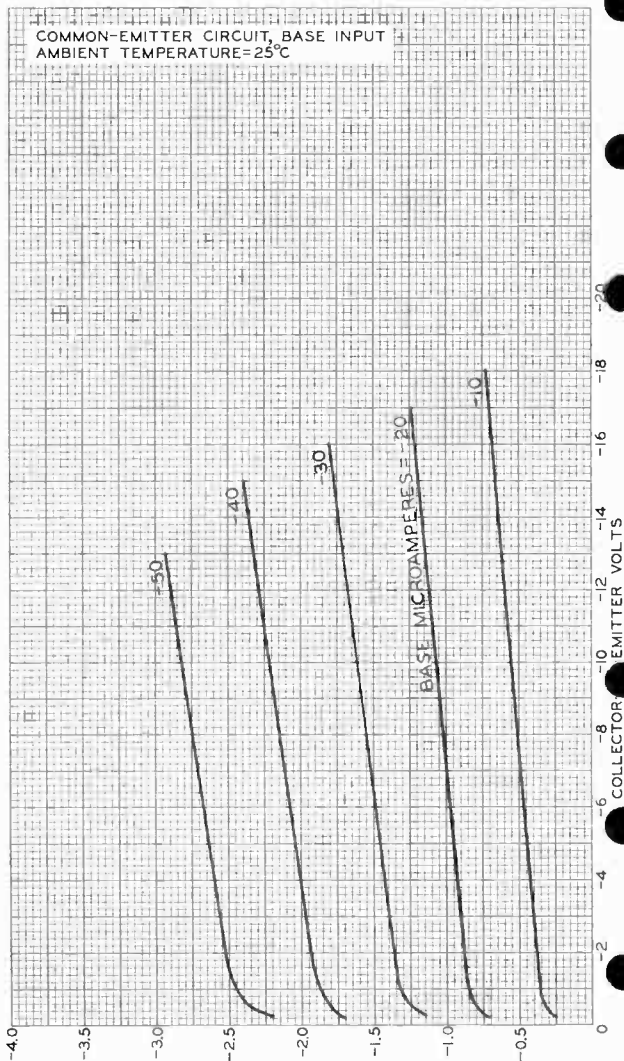
2N139



2N139

### AVERAGE COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE = 25°C



COLLECTOR MILLIAMPERES  
SEMICONDUCTOR DIVISION

92CM-8849RI

RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

World Radio History



2N140

# 2N140

## JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For 540 to 1600 kc converter applications

### GENERAL DATA

#### Electrical:

Minimum DC Collector-to-Base Voltage for dc collector current of $-10 \mu\text{amp}$ with emitter open, and at ambient temperature of $25^{\circ}\text{C}$ . . . . .	-16	volts
Maximum DC Collector Current for dc collector-to-base voltage of $-12$ volts with emitter open, and at ambient temperature of $25^{\circ}\text{C}$ . . . . .	-6	$\mu\text{amp}$
Maximum DC Emitter Current for dc emitter-to-base voltage of $-12$ volts with collector open, and at ambient temperature of $25^{\circ}\text{C}$ . . . . .	-40	$\mu\text{amp}$

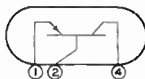
#### Mechanical:

Mounting Position . . . . .	Any
Maximum Overall Length . . . . .	0.697"
Maximum Seated Length . . . . .	0.495"
Maximum Diameter . . . . .	0.260"
Dimensional Outline . . . . .	See front of this Section
Case . . . . .	Metal, Insulated
Envelope Seals . . . . .	Hermetic
Base . . . . .	Small-Round Linotetrar 3-Pin (JEDEC No. E3-25)

Pin 1 - Emitter

Pin 4 - Collector

Pin 2 - Base



### CONVERTER SERVICE

#### Maximum Ratings, Absolute Values:

DC COLLECTOR-TO-BASE VOLTAGE . . . . .	-16 max.	volts
DC EMITTER-TO-BASE VOLTAGE . . . . .	-12 max.	volts
DC COLLECTOR CURRENT . . . . .	-15 max.	ma
DC EMITTER CURRENT . . . . .	15 max.	ma
COLLECTOR DISSIPATION . . . . .	35 max.	mw
AMBIENT TEMPERATURE (During operation) . . . . .	70 max.	$^{\circ}\text{C}$
STORAGE-TEMPERATURE RANGE . . . . .	-55 to +85	$^{\circ}\text{C}$

#### Characteristics, At Ambient Temperature of $25^{\circ}\text{C}$ :

Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage . . . . .	-9	volts
DC Collector Current . . . . .	-0.6	ma
Current Transfer Ratio ( $\alpha_f$ ) <sup>■</sup> . . . . .	-48	

<sup>■</sup>: See next page.



2N140

## JUNCTION TRANSISTOR

Small-Signal Hybrid- $\pi$  Parameters:\*

DC Collector-to-Emitter Voltage ( $V_{CE}$ ) . . .	-9	volts
DC Collector Current ( $I_C$ ) . . . . .	-0.6	ma
Resistance $r_{bb'}$ . . . . .	85	ohms
Conductance $g_{b'e}$ . . . . .	480	$\mu$ hos
Conductance $g_{ce}$ . . . . .	5.4	$\mu$ hos
Conductance $g_{b'c}$ . . . . .	0.23	$\mu$ ho
Capacitance $C_{b'e}$ . . . . .	650	$\mu$ f
Capacitance $C_{b'c}$ . . . . .	9.5	$\mu$ f
Intrinsic Transconductance ( $g_m$ ) . . . . .	22600	$\mu$ hos
Frequency for unity power amplification .	16.5	Mc

## Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage . . . . .	-9	volts
DC Collector Current . . . . .	-0.6	ma
Current Transfer Ratio <sup>■</sup> . . . . .	0.980	
Frequency at which the current transfer ratio drops to one-half the square root of two times its value at 1 kc . . . . .	7	Mc

## Typical Operation, At Ambient Temperature of 25°C:

## Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage . . . . .	-9	volts
DC Collector Current . . . . .	-0.6	ma
Input Resistance . . . . .	600	ohms
Output Resistance . . . . .	75000	ohms
<b>RMS Base-to-Emitter Oscillator</b>		
Injection Voltage . . . . .	100	mv
Signal Frequency . . . . .	1	Mc
Useful Conversion Power Gain . . . . .	30	db

\* As derived from corresponding equivalent circuit shown under type 2N104.

■ Measured at 1 kc.

● This frequency (figure of merit) may be calculated from the equation

$$f = \frac{1}{4\pi} \sqrt{\frac{g_m}{r_{bb'} \cdot C_{b'c} \cdot C_{b'e}}}$$

## OPERATING CONSIDERATIONS

The 2N140 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.



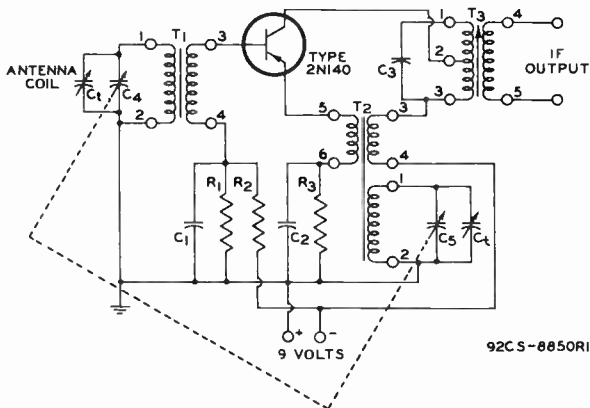


2N140

2N140

## JUNCTION TRANSISTOR

## TYPICAL SELF-EXCITED CONVERTER CIRCUIT



C1: 0.05  $\mu\text{f}$   
 C2: 0.04  $\mu\text{f}$   
 C3: 220  $\mu\text{f}$   
 C4: 12 to 230  $\mu\text{f}$  (variable)  
 C5: 10 to 105  $\mu\text{f}$  (variable)

Ct: 2 to 20  $\mu\text{f}$  (variable)  
 R1: 6800 ohms  
 R2: 18000 ohms  
 R3: 3900 ohms

T1: RF Transformer; low-loss ferrite core; unloaded Q (mounted in chassis), 212 at 1 Mc. Primary: 75 turns of 7/41 Litz wire space wound (spacing equal to diameter of wire) in single layer and centered on core; reflected resistance with secondary terminated, 0.3 megohm; inductance (approx.), 353 microhenries. Secondary: 4.5 turns of No. 34 SSE wire wound on ground end of core.

T2: Oscillator Transformer; low-loss ferrite core; unloaded Q (mounted in chassis), 100 at 1.455 Mc. Primary: 133 turns of 7/41 Litz wire between terminals 1 and 2; inductance (approx.); 207 microhenries. Secondary: 10 turns of No. 34 SSE wire between terminals 3 and 4; 4 turns of No. 34 SSE wire between terminals 5 and 6.

T3: IF Transformer; ferrite core; unloaded Q (mounted in chassis), 110 at 455 kc; loaded Q (mounted in chassis), 35 at 455 kc. Turns ratios: terminals 1 and 3 to terminals 2 and 3, 1.17; terminals 2 and 3 to terminals 4 and 5, 14.35; terminals 1 and 3 to terminals 4 and 5, 16.8. Primary: reflected resistance with secondary terminated, 0.206 megohm. Secondary: reflected resistance with primary terminated, 1000 ohms.

Devices and arrangements shown or described herein may use patents of RCA or others. Information contained herein is furnished without responsibility by RCA for its use and without prejudice to RCA's patent rights.

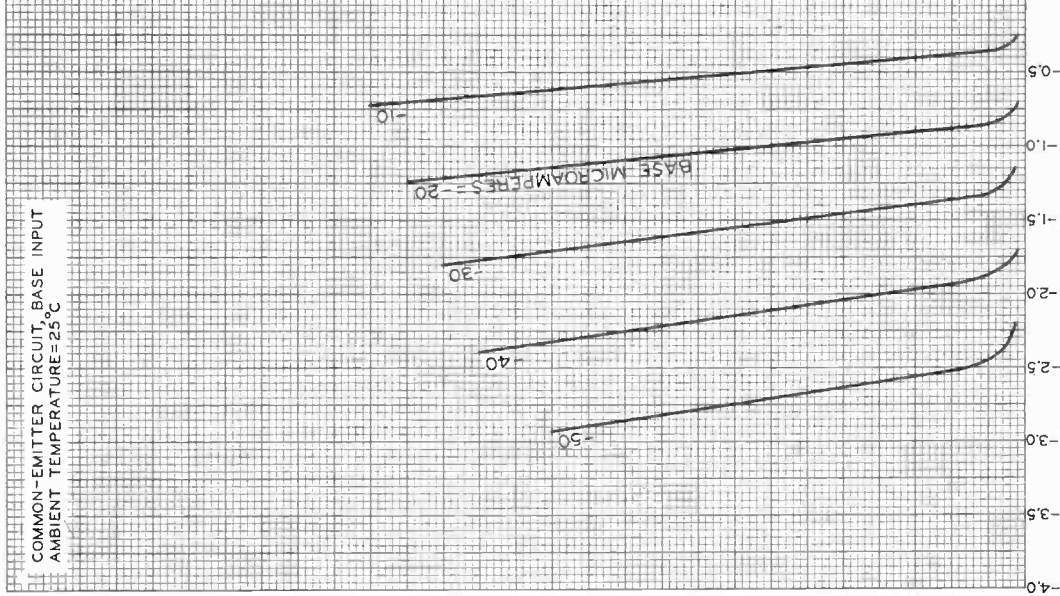


2N140

2N140

# AVERAGE COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE = 25°C



COLLECTOR MILLIAMPERES

SEMICONDUCTOR DIVISION

RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

92CM-9015

## Power Transistor

## GERMANIUM P-N-P ALLOY TYPE

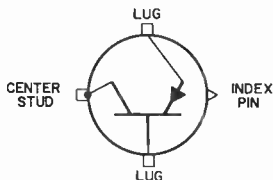
For Power Switching and Amplifier Service  
in Industrial and Military Applications

## GENERAL DATA

## Mechanical:

Operating Position . . . . .	Any
Maximum Seated Length . . . . .	0.520"
Maximum Diameter . . . . .	1.250"
Dimensional Outline . . . . .	JEDEC No. TO-36
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic
Terminal Diagram (See <i>Dimensional Outline</i> ):	

BOTTOM VIEW



## INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and audio-amplifier, relay- and solenoid-actuating circuits

## Maximum and Minimum Ratings, Absolute-Maximum Values:

## COLLECTOR-TO-BASE VOLTAGE:

With emitter-to-base reverse biased

(DC emitter-to-base volts = 1.5) . . . . .	-60 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-40 max.	volts
COLLECTOR CURRENT . . . . .	-15 max.	amp
EMITTER CURRENT . . . . .	15 max.	amp
BASE CURRENT . . . . .	-4 max.	amp

TRANSISTOR DISSIPATION:<sup>a</sup>

At case temperatures<sup>b</sup> of 25° C or below . . . . . 150 max. watts

CASE TEMPERATURE<sup>b</sup> RANGE:

Operating and storage . . . . . -65 to +100 °C

## Typical Operation:

In a common-emitter, base-input, power-switching circuit at case temperature<sup>b</sup> of 25° C

DC Supply Voltage . . . . .	-12	volts
DC Base-Bias Voltage . . . . .	6	volts
"On" DC Collector Current . . . . .	-12	amp
"Turn-On" Base Current . . . . .	-2	amp
"Turn-Off" Base Current . . . . .	0	amp

← Indicates a change.



# 2N173

## Switching Time:

Rise time . . . . .	15	$\mu$ sec
Fall time . . . . .	15	$\mu$ sec

<sup>a</sup> See accompanying *Rating Chart* and also *Transistor-Dissipation Rating Chart* in General Section.

<sup>b</sup> Measured at any point on seating surface.

## ELECTRICAL CHARACTERISTICS

*Voltage values are given with respect to base and at case temperature<sup>b</sup> of 25° C unless otherwise specified*

*Min. Typical Max.*

### DC Collector-to-Emitter

#### Breakdown Voltage:

With base connected to emitter, dc collector

amperes = -0.3 . . . . .  $BV_{CES}$  -50 - - - volts

With base open:

For dc collector amperes = -0.3 . . . . .  $BV_{CEO}$  - - -50 - - volts

For dc collector amperes = -1<sup>c</sup> . . . . . -45 - - - volts

### DC Base-to-Emitter Voltage

for dc collector-to-emitter volts = -2, dc collector amperes = -5. . . . .  $V_{BE}$  - -0.65 - - volt

### DC Collector-to-Emitter

Saturation Voltage for dc collector amperes = -12, dc base amperes = -2. . . . .  $V_{CE}$  - -0.3 -0.7 volt

### DC Emitter Voltage for dc collector volts = -80, dc emitter current = 0. . . . . $V_{EB}$ - -0.15 -1 volt

DC Punch-Through Voltage. . . . .  $V_{PT}$  -60 - - - volts

### DC Emitter-Cutoff Current

for dc emitter volts = -40, dc collector current = 0 . . . . .  $I_{EBO}$  - -1 -4 ma

### DC Collector-Cutoff Current:

With dc collector volts = -2, dc emitter current = 0 . . . . .  $I_{CBO}$  - -100 -  $\mu$ a

With dc collector volts = -60, dc emitter current = 0 . . . . . - -2 -4  $\mu$ a

With dc collector volts = -60, dc emitter current = 0, case temperature<sup>b</sup> = 71° C. . . . . - - -15 ma

→ Indicates a change.



DC Current Transfer Ratio for dc collector-to-emitter volts = -2, dc collector amperes =	$h_{FE}$				
-5 . . . . .		35	-	70	
-12 . . . . .		-	25	-	
Beta-Cutoff Frequency for dc collector-to-emitter volts = -6, dc collector amperes = -5 . . . . .	$f_{ae}$	-	10	-	kc
Thermal Resistance: Junction-to-case . . . . .	$R_T$	-	0.35	0.5	$^{\circ}\text{C}/\text{watt}$
Thermal Capacity for pulse duration of 1 to 10 milliseconds . . . . .		-	0.075	-	$\text{watt-sec}/^{\circ}\text{C}$
Thermal Time Constant . . .	$\tau_1$	-	26.25	-	msec

<sup>b</sup> Measured at any point on seating surface.

<sup>c</sup> Tested by sweep method to prevent excessive heating of collector junction.

### PERFORMANCE TESTS

This transistor type is designed to pass the environmental tests specified in Military Specification MIL-S-19500B.

### OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

Electrical connection can be made to the base and emitter lugs by means of clips or by soldering directly to the lugs. When soldering connections are made to the lugs, care should be taken to conduct excessive heat away from the lug seals, otherwise the heat of the soldering operation will crack the glass seals of the lugs and damage the transistor.

This transistor is provided with a single-ended stud for mounting to a heat sink and for electrical connection to the collector. (See accompanying *Suggested Mounting Arrangement*). Electrical connection to the base and to the emitter is made to their respective lugs.

It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.

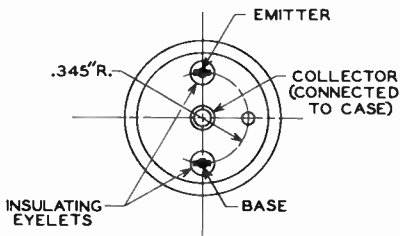
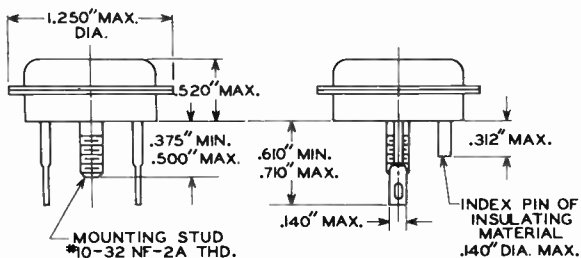
The maximum torque on mounting stud should not exceed 12 inch-pounds.

← Indicates a change.



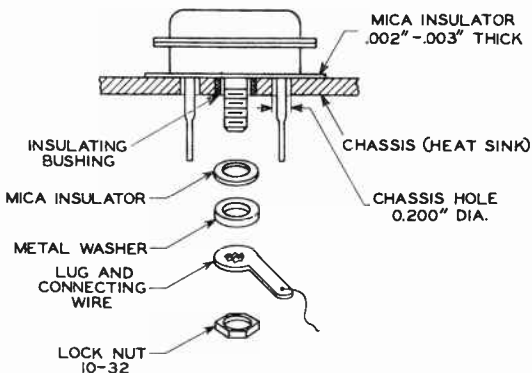
# 2N173

JEDEC No. T0-36



92CM-10612RI

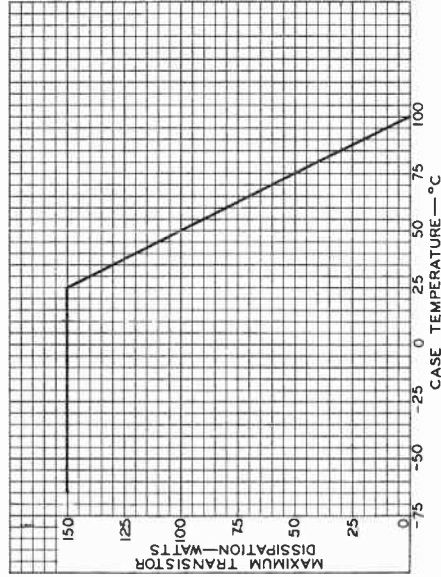
## SUGGESTED MOUNTING ARRANGEMENT



92CS-10624RI

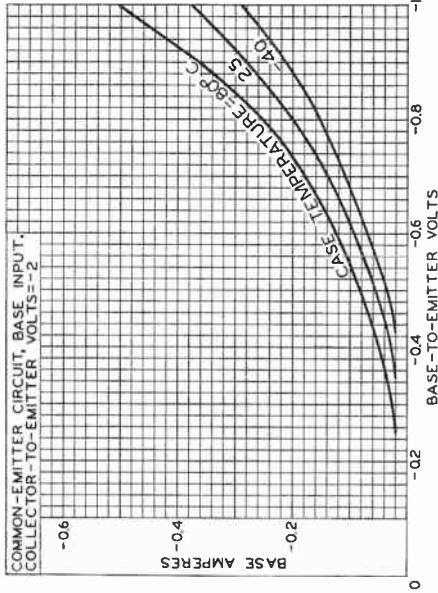


## RATING CHART



92CS-10702RI

## TYPICAL BASE CHARACTERISTICS

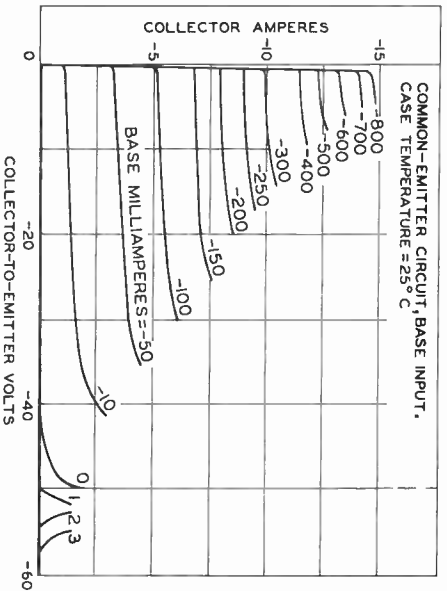


92CS-10703

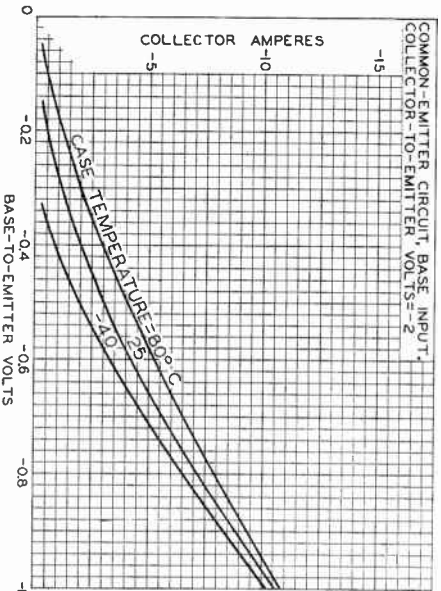


# 2N173

## TYPICAL COLLECTOR CHARACTERISTICS



## TYPICAL CHARACTERISTICS





## Power Transistor

## GERMANIUM P-N-P ALLOY TYPE

For Power Switching and Amplifier Service  
in Industrial and Military Applications

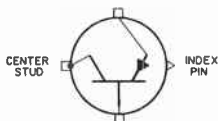
## GENERAL DATA

## Mechanical:

Operating Position . . . . .	Any
Maximum Overall Length . . . . .	1.230"
Maximum Seated Length . . . . .	0.520"
Maximum Diameter . . . . .	1.250"
Dimensional Outline . . . . .	JEDEC No. TO-36
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic

Terminal Diagram (See *Dimensional Outline*):

## BOTTOM VIEW



## INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter, chopper,  
voltage- and current-regulator, dc- and audio-  
amplifier, relay- and solenoid-actuating circuits

## Maximum and Minimum Ratings, Absolute-Maximum Values:

## COLLECTOR-TO-BASE VOLTAGE:

With emitter-to-base reverse biased

(DC emitter-to-base volts = 1.5) . . . . . -60 max. volts

EMITTER-TO-BASE VOLTAGE . . . . . -40 max. volts

COLLECTOR CURRENT . . . . . -15 max. amp

EMITTER CURRENT . . . . . 15 max. amp

BASE CURRENT . . . . . -4 max. amp

TRANSISTOR DISSIPATION:<sup>A</sup>

At case temperature of 25° C. . . . . 70 max. watts

## CASE-TEMPERATURE RANGE:

Continuous operation . . . . . -65 to +95 °C

Intermittent operation . . . . . -65 to +100 °C

Storage . . . . . -65 to +100 °C

## Typical Operation:

In a common-emitter, base-input, power-  
switching circuit at case temperature of 25° C

DC Supply Voltage . . . . . -12 volts

DC Base-Bias Voltage . . . . . 6 volts

"On" DC Collector Current . . . . . -12 amp

"Turn-On" Base Current . . . . . -2 amp

"Turn-Off" Base Current . . . . . 0 amp



# 2N173

## Switching Time:

Rise time. . . . .	15	$\mu$ sec
Fall time. . . . .	15	$\mu$ sec

▲ See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and case temperature of 25° C unless otherwise specified

Min. Typical Max.

### DC Collector-to-Emitter Break-down Voltage:

With base connected to emitter, dc collector amperes = -0.3 . . . . .	$BV_{CES}$	-50	-	-	volts
With base open:	$BV_{CEO}$				
For dc collector amperes = -0.3 . . . . .			-50	-	volts
For dc collector amperes = -1 . . . . .		-45	-	-	volts

### DC Base-to-Emitter Voltage\*

for dc collector-to-emitter volts = -2, dc collector amperes = -5 . . . . .	$V_{BE}$	-	-0.65	-	volt
---	----------	---	-------	---	------

### DC Collector-to-Emitter

Saturation Voltage* for dc collector amperes = -12, base amperes = -2 . . . . .	$V_{CE}$	-	-0.3	-1	volt
---	----------	---	------	----	------

### DC Emitter Voltage for dc

collector volts = -60, emitter amperes = 0 . . . . .	$V_{EB}$	-	-0.15	-1	volt
--	----------	---	-------	----	------

### DC Punch-Through Voltage . . . . .

	$V_P$	-60	-	-	volts
--	-------	-----	---	---	-------

### DC Emitter-Cutoff Current

for dc emitter volts = -40, dc collector amperes = 0 . . . . .	$I_{EBO}$	-	-1	-8	ma
--	-----------	---	----	----	----

### DC Collector-Cutoff Current:

With dc collector volts = -2, dc emitter amperes = 0 . . . . .	$I_{CBO}$	-	-100	-	$\mu$ a
--	-----------	---	------	---	---------

With dc collector volts = -60, dc emitter amperes = 0 . . . . .		-	-2	-8	$\mu$ a
---	--	---	----	----	---------

With dc collector volts = -60, dc emitter amperes = 0, case temperature = 71° C . . . . .		-	-	-15	ma
---	--	---	---	-----	----

### DC Current Transfer Ratio\*

for dc collector-to-emitter volts = -2, dc collector amperes =	$h_{FE}$				
-5 . . . . .		35	-	70	
-12 . . . . .		-	25	-	



Beta-Cutoff Frequency* for dc collector-to-emitter volts = -6, dc collector amperes = -5. . . . .	$f_{ae}$	-	10	-	kc
Thermal Resistance:					
Junction-to-case. . . . .	$R_T$	-	0.7	1	$^{\circ}\text{C}/\text{watt}$
Thermal Capacity for pulse duration of 1 to 10 milliseconds. . . . .		-	0.075	-	watt-sec/ $^{\circ}\text{C}$
Thermal Time Constant . . . . .	$\tau_1$	-	52.5	-	msec

\* Sweep voltage used to perform test.

\* Measured in a common-emitter, base-input circuit.

### OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

Electrical connection can be made to the base and emitter terminals by means of clips or by soldering directly to the terminals. When soldering connections are made to the terminals, care should be taken to conduct excessive heat away from the terminal seals, otherwise the heat of the soldering operation will crack the glass seals of the terminals and damage the transistor.

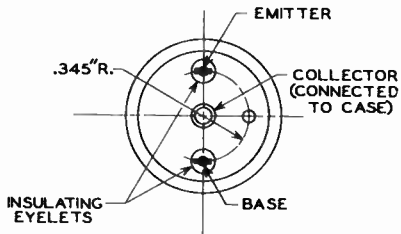
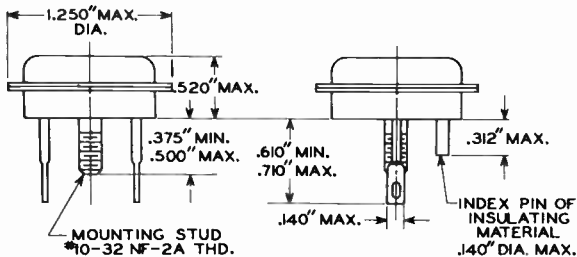
This transistor is provided with a single-ended stud for mounting to a heat sink and for electrical connection to the collector. (See accompanying *Suggested Mounting Arrangement*). Electrical connection to the base and to the emitter is made to their respective terminals.

It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.

The maximum torque on mounting stud should not exceed 12 inch-pounds.

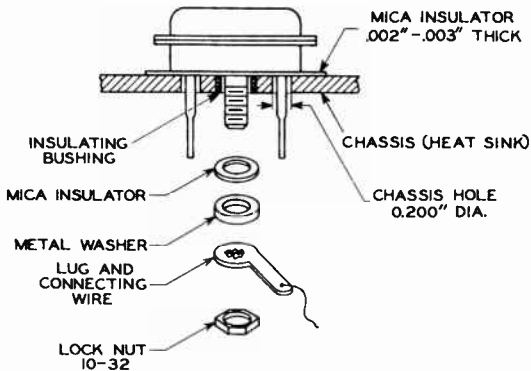


# 2N173



92CM-10612RI

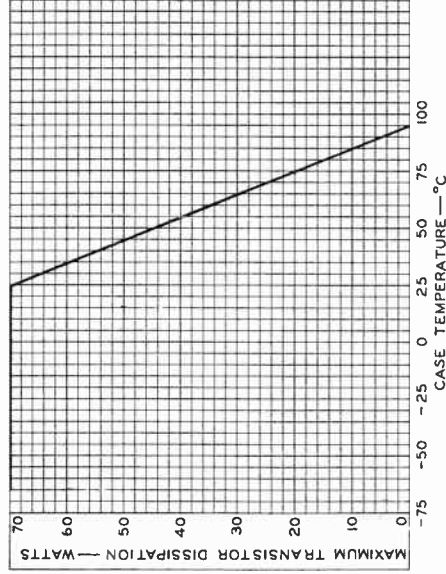
## SUGGESTED MOUNTING ARRANGEMENT



92CS-10624RI

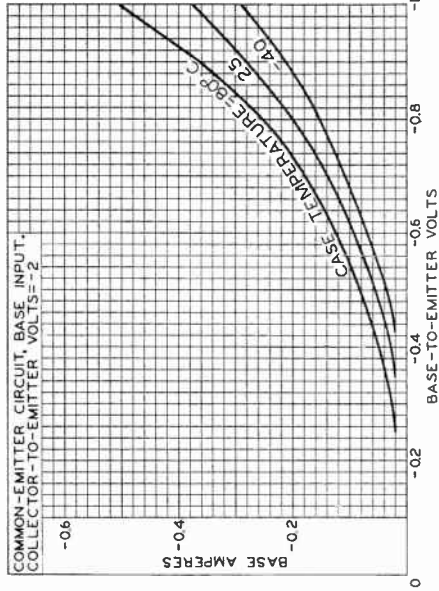


## RATING CHART



92CS-10701

## TYPICAL BASE CHARACTERISTICS

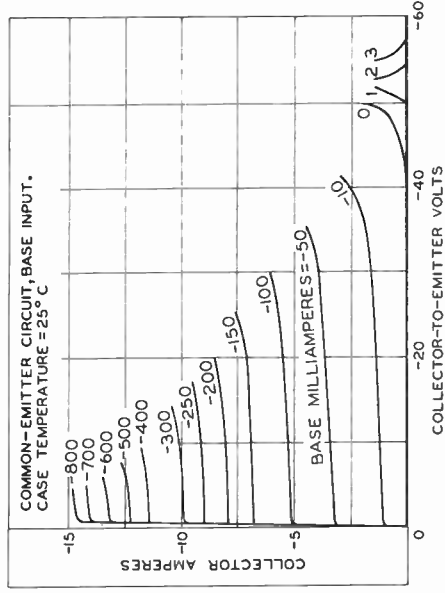


92CS-10703



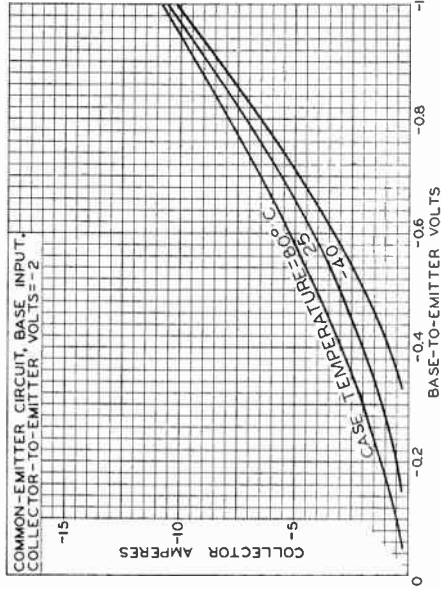
# 2N173

## TYPICAL COLLECTOR CHARACTERISTICS



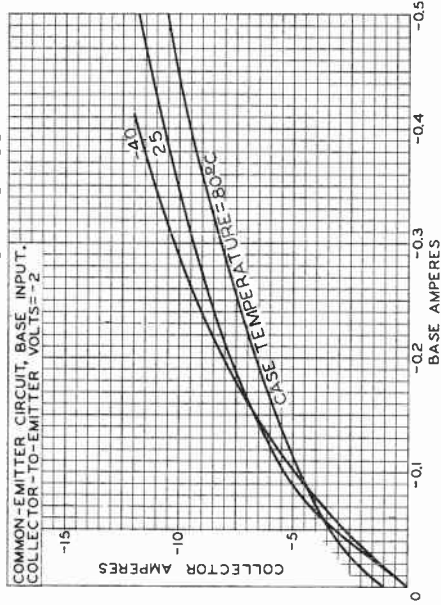
92CS-10722

## TYPICAL CHARACTERISTICS



92CS-10709

## TYPICAL CHARACTERISTICS



92CS-10712







## Power Transistor

## GERMANIUM P-N-P ALLOY TYPE

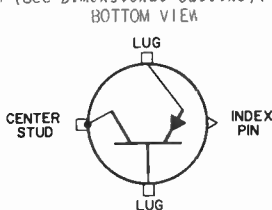
For Power Switching and Amplifier Service  
in Industrial and Military Applications

## GENERAL DATA

## Mechanical:

Operating Position . . . . .	Any
Maximum Seated Length . . . . .	0.520"
Maximum Diameter . . . . .	1.250"
Dimensional Outline . . . . .	JEDEC No. TO-36
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic

Terminal Diagram (See *Dimensional Outline*):



## INDUSTRIAL SERVICE

*Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and audio-amplifier, relay- and solenoid-actuating circuits*

## Maximum and Minimum Ratings, Absolute-Maximum Values:

## COLLECTOR-TO-BASE VOLTAGE:

With emitter-to-base reverse biased (DC emitter-to-base volts = 1.5) . . . . .	-80 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-60 max.	volts
COLLECTOR CURRENT . . . . .	-15 max.	amp
EMITTER CURRENT . . . . .	15 max.	amp
BASE CURRENT . . . . .	-4 max.	amp
TRANSISTOR DISSIPATION: <sup>a</sup>		
At case temperatures <sup>b</sup> of 25° C or below . . . . .	150 max.	watts
CASE-TEMPERATURE <sup>b</sup> RANGE:		
Operating and storage . . . . .	-65 to +100	°C

## Typical Operation:

*In a common-emitter, base-input, power-switching circuit at case temperature<sup>b</sup> of 25° C*

DC Supply Voltage . . . . .	-12	volts
DC Base-Bias Voltage . . . . .	6	volts
"On" DC Collector Current . . . . .	-12	amp
"Turn-On" Base Current . . . . .	-2	amp
"Turn-Off" Base Current . . . . .	0	amp

← Indicates a change.



# 2N174

## Switching Time:

Rise time . . . . .	15	$\mu$ sec
Fall time . . . . .	15	$\mu$ sec

<sup>a</sup> See accompanying *Rating Chart* and also *Transistor-Dissipation Rating Chart* in General Section.

<sup>b</sup> Measured at any point on seating surface.

## ELECTRICAL CHARACTERISTICS

*Voltage values are given with respect to base and at case temperature<sup>b</sup> of 25° C unless otherwise specified*

*Min. Typical Max.*

DC Collector-to-Emitter Breakdown Voltage:						
With base connected to emitter, dc collector amperes = -0.3 . . . . .						
	$BV_{CES}$	-70	-	-		volts
With base open: For dc collector amperes = -1° . . . . .						
	$BV_{CEO}$	-55	-	-		volts
DC Base-to-Emitter Voltage for dc collector-to-emitter volts = -2, dc collector amperes = -5. . . . .						
	$V_{BE}$	-	-0.65	-0.9		volt
DC Collector-to-Emitter Saturation Voltage for dc collector amperes = -12, dc base amperes = -2. . . . .						
	$V_{CE}$	-	-0.3	-0.7		volt
DC Emitter Voltage for dc collector volts = -80, dc emitter current = 0. . . . .						
	$V_{EB}$	-	-	-1		volt
DC Punch-Through Voltage. . . . .						
	$V_{PT}$	-80	-	-		volts
DC Emitter-Cutoff Current for dc emitter volts = -60, dc collector current = 0 . . . . .						
	$I_{EBO}$	-	-1	-4		ma
DC Collector-Cutoff Current: With dc collector volts = 2, dc emitter current = 0 . . . . .						
	$I_{CBO}$	-	-100	-		$\mu$ a
With dc collector volts = -80, dc emitter current = 0 . . . . .						
		-	-2	-4		ma
With dc collector volts = -80, dc emitter current = 0, case temperature <sup>b</sup> = 71° C . . . . .						
		-	-	-15		ma
DC Current Transfer Ratio for dc collector-to-emitter volts = -2, dc collector amperes =						
	$h_{FE}$					
-5. . . . .		25	-	50		
-12 . . . . .		-	20	-		

→ Indicates a change.



Beta-Cutoff Frequency for dc collector-to-emitter volts = -6, dc collector amperes = -5. . . . .	$f_{ae}$	-	10	-	kc
Thermal Resistance: Junction-to-case. . . . .	$R_T$	-	0.35	0.5	$^{\circ}\text{C}/\text{watt}$
Thermal Capacity for pulse duration of 1 to 10 milliseconds. . . . .		-	0.075	-	watt- sec/ $^{\circ}\text{C}$
Thermal Time Constant . . . . .	$\tau_i$	-	26.25	-	msec

<sup>b</sup> Measured at any point on seating surface.

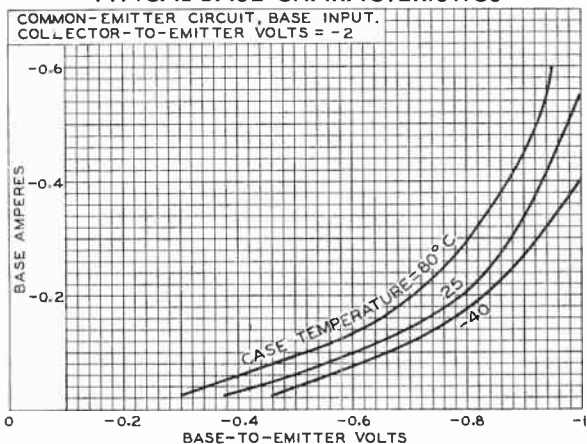
<sup>c</sup> Tested by sweep method to prevent excessive heating of collector junction.

**PERFORMANCE TESTS,  
OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
and  
RATING CHART**

shown under Type 2N173 also apply to the 2N174

← Indicates a change.

## TYPICAL BASE CHARACTERISTICS

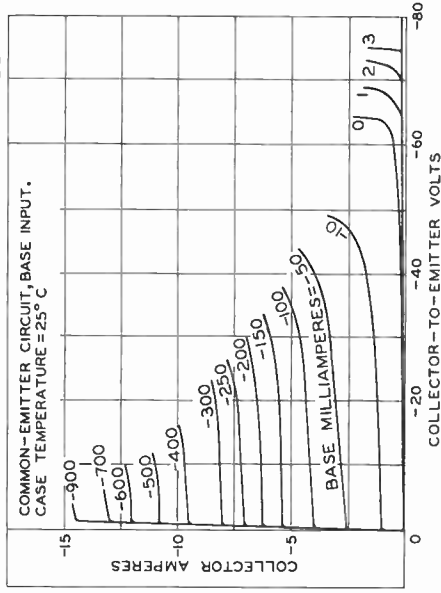


92CS-10706

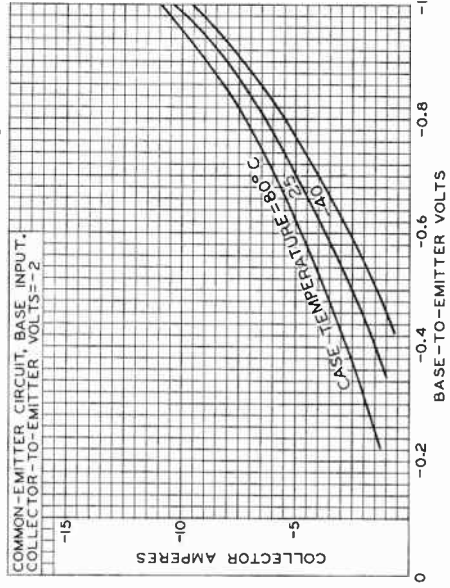


# 2N174

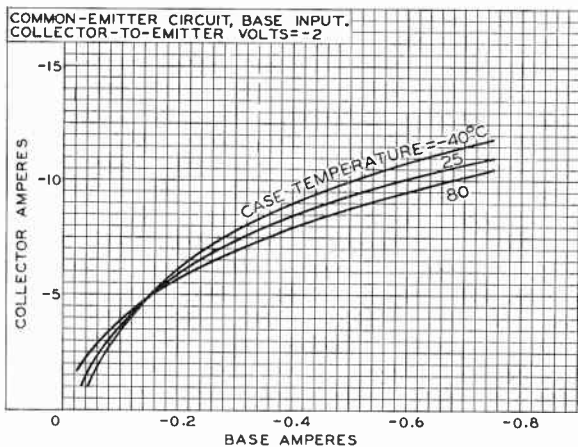
## TYPICAL COLLECTOR CHARACTERISTICS



## TYPICAL CHARACTERISTICS



## TYPICAL CHARACTERISTICS



92CS-10711





## Power Transistor

GERMANIUM P-N-P ALLOY TYPE

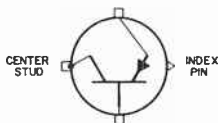
For Power Switching and Amplifier Service  
in Industrial and Military Applications

## GENERAL DATA

## Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	1.230"
Maximum Seated Length. . . . .	0.520"
Maximum Diameter. . . . .	1.250"
Dimensional Outline. . . . .	JEDEC No. TO-36
Case. . . . .	Welded, Metal
Seals. . . . .	Hermetic
Terminal Diagram (See <i>Dimensional Outline</i> ):	

BOTTOM VIEW



## INDUSTRIAL SERVICE

*Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and audio-amplifier, relay- and solenoid-actuating circuits*

## Maximum and Minimum Ratings, Absolute-Maximum Values:

## COLLECTOR-TO-BASE VOLTAGE:

With emitter-to-base reverse biased

(DC emitter-to-base volts = 1.5). . . . . -80 max. volts

EMITTER-TO-BASE VOLTAGE . . . . . -60 max. volts

COLLECTOR CURRENT . . . . . -15 max. amp

EMITTER CURRENT . . . . . 15 max. amp

BASE CURRENT. . . . . -4 max. amp

## TRANSISTOR DISSIPATION: ▲

At case temperature of 25° C. . . . . 87.5 max. watts

## CASE-TEMPERATURE RANGE:

Continuous operation. . . . . -65 to +95 °C

Intermittent operation. . . . . -65 to +100 °C

Storage . . . . . -65 to +100 °C

## Typical Operation:

*In a common-emitter, base-input, power-switching circuit at case temperature of 25° C*

DC Supply Voltage . . . . . -12 volts

DC Base-Bias Voltage. . . . . 6 volts

"On" DC Collector Current . . . . . -12 amp

"Turn-On" Base Current. . . . . -2 amp

"Turn-Off" Base Current . . . . . 0 amp



RADIO CORPORATION OF AMERICA

Semiconductor &amp; Materials Division

Somerville, N. J.

World Radio History

DATA 1

2-61

# 2N174

## Switching Time:

Rise time . . . . .	15	$\mu$ sec
Fall time . . . . .	15	$\mu$ sec

▲ See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and case temperature of 25° C unless otherwise specified

*V<sub>in</sub>*. Typical Max.

DC Collector-to-Emitter Breakdown Voltage:						
With base connected to emitter, dc collector amperes = -0.3 . . . . .						
$BV_{CES}$	-70	-	-			volts
With base open: For dc collector amperes = -1 . . . . .						
$BV_{CEO}$	-55	-	-			volts
DC Base-to-Emitter Voltage* for dc collector-to-emitter volts = -2, dc collector amperes = -5 . . . . .						
$V_{BE}$	-	-0.65	-0.9			volt
DC Collector-to-Emitter Saturation Voltage* for dc collector amperes = -12, base amperes = -2 . . . . .						
$V_{CE}$	-	-0.3	-0.9			volt
DC Emitter Voltage for dc collector volts = -80, emitter amperes = 0 . . . . .						
$V_{EB}$	-	-	-1			volt
DC Punch-Through Voltage . . . . .						
$V_P$	-80	-	-			volts
DC Emitter-Cutoff Current for dc emitter volts = -60, dc collector amperes = 0 . . . . .						
$I_{EBO}$	-	-1	-8			ma
DC Collector-Cutoff Current: With dc collector volts = 2, dc emitter amperes = 0 . . . . .						
$I_{CBO}$	-	-100	-			$\mu$ a
With dc collector volts = -80, dc emitter amperes = 0 . . . . .						
	-	-2	-8			ma
With dc collector volts = -80, dc emitter amperes = 0, case temperature = 71° C . . . . .						
	-	-	-15			ma
DC Current Transfer Ratio* for dc collector-to-emitter volts = -2, dc collector amperes =						
	-5 . . . . .	25	-	50		
	-12 . . . . .	-	20	-		





Beta-Cutoff Frequency* for dc collector-to-emitter volts = -6, dc collector amperes = -5. . . . .	$f_{ae}$	-	10	-	kc
Thermal Resistance: Junction-to-case. . . . .	$R_T$	-	0.5	0.8	$^{\circ}\text{C}/\text{watt}$
Thermal Capacity for pulse duration of 1 to 10 milliseconds. . . . .		-	0.075	-	$\text{watt-sec}/^{\circ}\text{C}$
Thermal Time Constant . . . . .	$\tau_1$	-	37.5	-	msec

\* Sweep voltage used to perform test.

\* Measured in a common-emitter, base-input circuit.

### OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

Electrical connection can be made to the base and emitter terminals by means of clips or by soldering directly to the terminals. When soldering connections are made to the terminals, care should be taken to conduct excessive heat away from the terminal seals, otherwise the heat of the soldering operation will crack the glass seals of the terminals and damage the transistor.

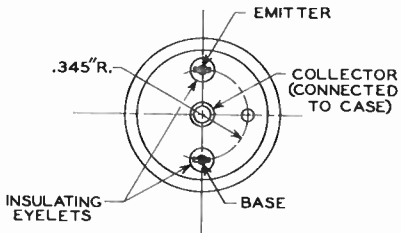
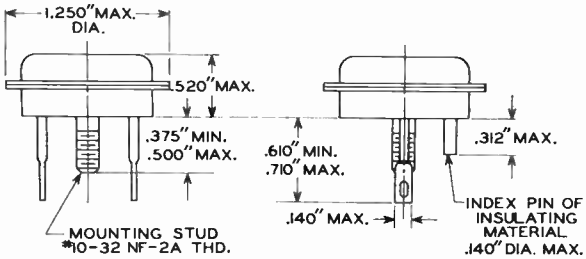
This transistor is provided with a single-ended stud for mounting to a heat sink and for electrical connection to the collector. (See accompanying *Suggested Mounting Arrangement*). Electrical connection to the base and to the emitter is made to their respective terminals.

It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.

The maximum torque on mounting stud should not exceed 12 inch-pounds.

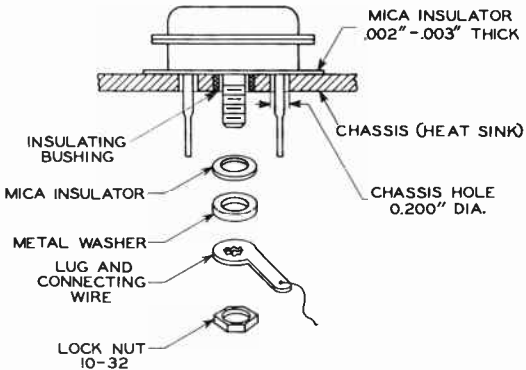


# 2N174



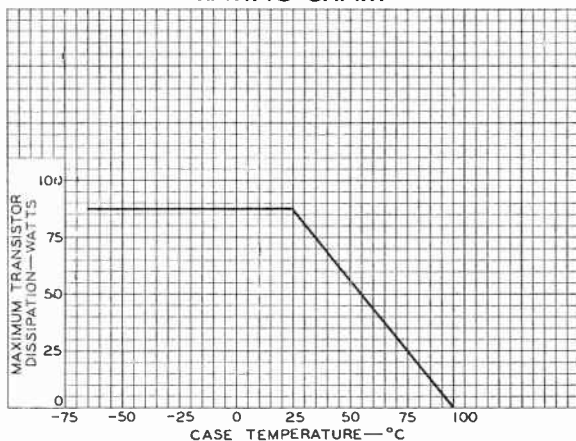
92CM-10612R1

## SUGGESTED MOUNTING ARRANGEMENT



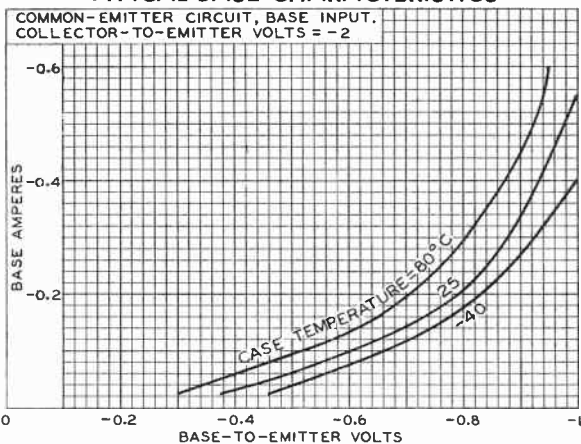
92CS-10624R1

## RATING CHART



92CS-10702

## TYPICAL BASE CHARACTERISTICS

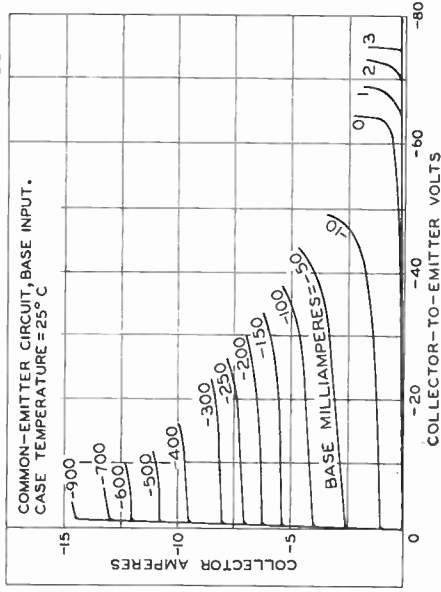


92CS-10706

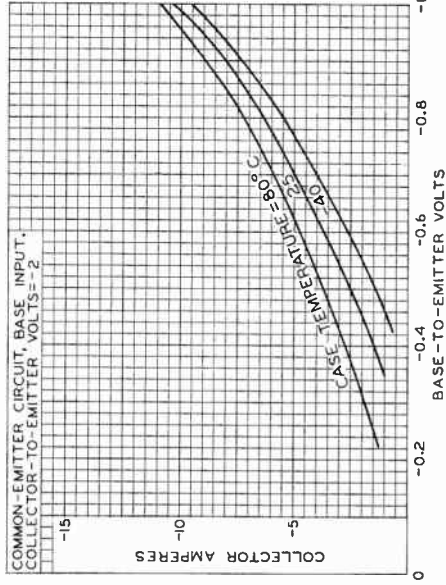


# 2N174

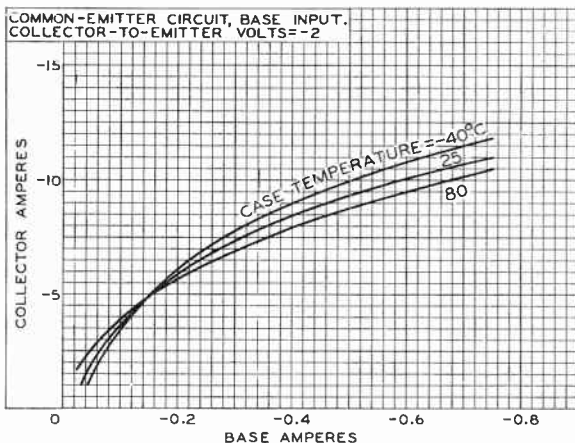
## TYPICAL COLLECTOR CHARACTERISTICS



## TYPICAL CHARACTERISTICS



## TYPICAL CHARACTERISTICS



92CS-10711







2N175

2N175

## JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For low-noise audio-frequency applications

## GENERAL DATA

## Electrical:

Maximum DC Collector Current for dc collector-to-base voltage of -25 volts with emitter open, and at ambient temperature of 25°C. . . . .	-12	$\mu$ amp
Maximum DC Emitter Current for dc emitter-to-base voltage of -12 volts with collector open, and at ambient temperature of 25°C. . . . .	-12	$\mu$ amp

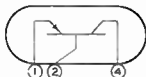
## Mechanical:

Mounting Position. . . . .	. . . . .	Any
Maximum Overall Length. . . . .	. . . . .	0.697"
Maximum Seated Length. . . . .	. . . . .	0.495"
Maximum Diameter. . . . .	. . . . .	0.260"
Dimensional Outline. . . . .	See front of this Section	
Case. . . . .	Metal, Insulated	
Envelope Seals. . . . .	Hermetic	
Base. . . . .	Small-Round Linotetrap 3-Pin (JEDEC No. E3-25)	

Pin 1 - Emitter

Pin 4 - Collector

Pin 2 - Base



## AUDIO-FREQUENCY AMPLIFIER -- Class A

## Maximum Ratings, Absolute Values:

DC COLLECTOR-TO-BASE VOLTAGE. . . . .	-10 max.	volts
DC EMITTER-TO-BASE VOLTAGE. . . . .	-10 max.	volts
DC COLLECTOR CURRENT. . . . .	-2 max.	ma
DC EMITTER CURRENT. . . . .	2 max.	ma
COLLECTOR DISSIPATION. . . . .	20 max.	mw
AMBIENT TEMPERATURE (During operation). . . . .	50 max.	°C
STORAGE-TEMPERATURE RANGE. . . . .	-55 to +85	°C

## Characteristics, At Ambient Temperature of 25°C:

## Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage. . . . .	-4	volts
DC Collector Current. . . . .	-0.5	ma

## Power Gain:

With load resistance = 0.07 megohm, and input resistance = 2000 ohms. . . . .	43	db
---	----	----

## Noise Factor:

Measured with a noise diode and thermocouple voltmeter with load resistance = 20,000 ohms, generator resistance = 1000 ohms, and equivalent noise bandwidth = 12.3 kc with geometric mean of 300 cps:		
Maximum value. . . . .	6	db



2N175

## JUNCTION TRANSISTOR

## Small-Signal T Parameters:\*

DC Collector-to-Emitter Voltage ( $V_{CE}$ ).	-4	volts
DC Collector Current ( $I_C$ ).	-0.5	ma
Emitter Resistance ( $r_e$ ).	37.7	ohms
Base Resistance ( $r_b$ ).	1085	ohms
Mutual Resistance ( $r_m$ ).	2.82	megohms
Collector Resistance ( $r_c$ ).	2.86	megohms
Current Transfer Ratio ( $\alpha_f$ ) <sup>†</sup> .	-65	

Small-Signal Hybrid- $\pi$  Parameters:\*

DC Collector-to-Emitter Voltage ( $V_{CE}$ ).	-4	volts
DC Collector Current ( $I_C$ ).	-0.5	ma
Resistance $r_{bb'}$ .	190	ohms
Conductance $g_{b'e}$ .	296	$\mu$ hos
Conductance $g_{ce}$ .	6.6	$\mu$ hos
Conductance $g_{b'c}$ .	0.279	$\mu$ ho
Capacitance $C_{b'e}$ .	3900	$\mu$ f
Capacitance $C_{b'c}$ .	36	$\mu$ f
Intrinsic Transconductance ( $g_m$ ).	19200	$\mu$ hos
Frequency <sup>‡</sup> for unity power amplification	2.06	Mc

## Small-Signal H Parameters:\*

DC Collector-to-Emitter Voltage ( $V_{CE}$ ).	-4	volts
DC Collector Current ( $I_C$ ).	-0.5	ma
Input Resistance, output circuit shorted ( $h_i$ ).	3570	ohms
Reverse Voltage Transfer Ratio, input circuit open ( $h_r$ ).	$9.44 \times 10^{-4}$	
Forward Current Transfer Ratio, output circuit shorted ( $h_f$ ).	65	
Output Conductance, input circuit open ( $h_o$ ).	25	$\mu$ hos

## Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage . . . . .	-4	volts
DC Collector Current . . . . .	-0.5	ma
Frequency at which the current transfer ratio drops to one-half the square root of two times its value at 1 kc.	0.85	Mc

## OPERATING CONSIDERATIONS

The 2N175 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

- As derived from corresponding equivalent circuit shown under type 2N104.
- Measured at 1 kc.
- This frequency (figure of merit) may be calculated from the equation

$$f = \frac{1}{4\pi} \sqrt{\frac{g_m}{r_{bb'} \cdot C_{b'c} \cdot C_{b'e}}}$$



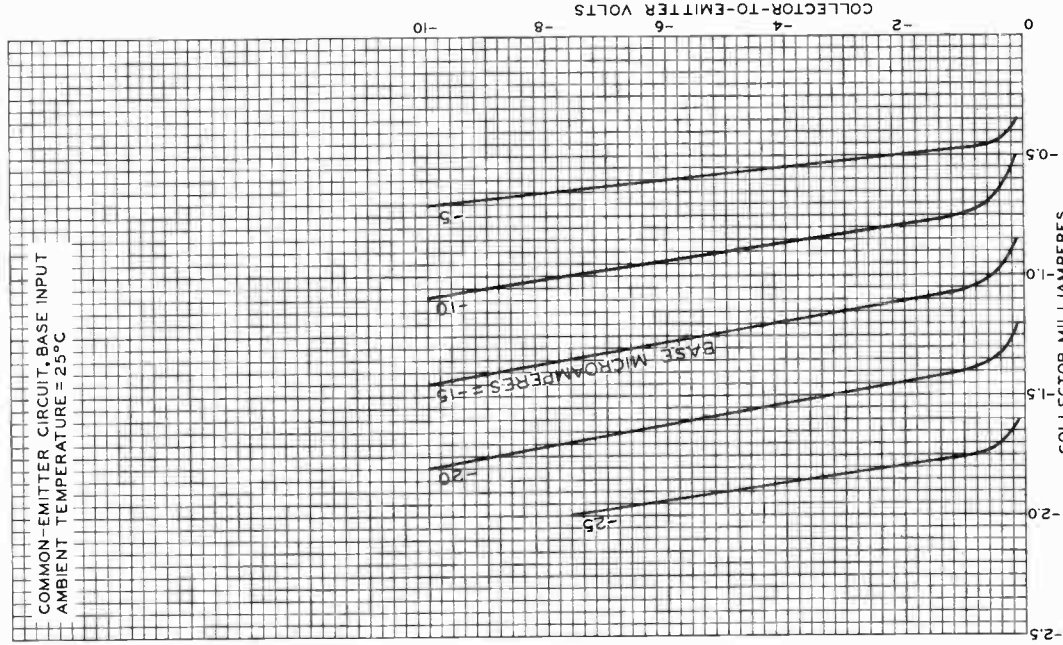


2N175

2N175

# AVERAGE COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE = 25°C



COLLECTOR MILLIAMPERES

SEMICONDUCTOR DIVISION

RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

92CM - 8914RI

2N175

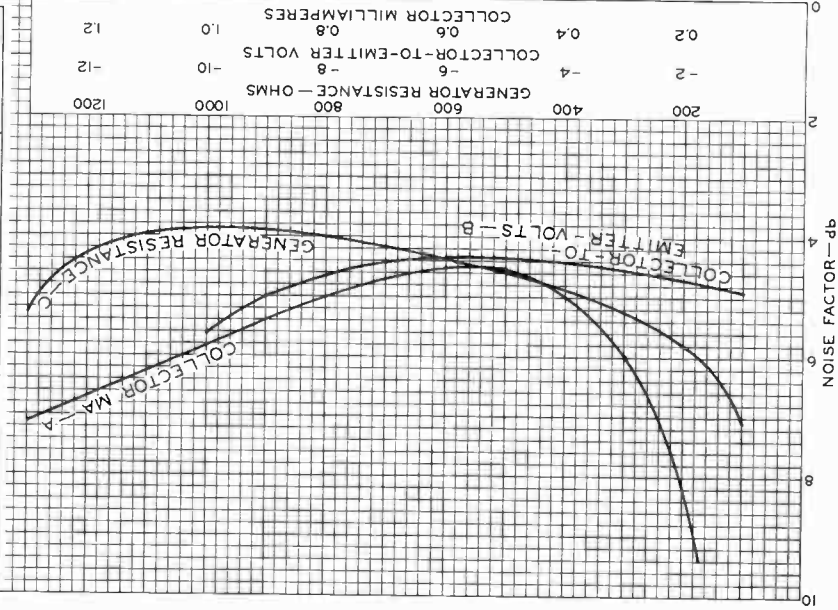


2N175

## TYPICAL NOISE CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
 AMBIENT TEMPERATURE = 25°C  
 MEASURED WITH A NOISE DIODE AND THERMOCOUPLE VOLT-  
 METER WITH LOAD RESISTANCE = 20000 OHMS AND EQUIVALENT  
 NOISE BANDWIDTH = 12.3 KC WITH GEOMETRIC MEAN OF 300 CPS

CURVE	GENERATOR RESISTANCE (OHMS)	COLLECTOR-TO-EMITTER VOLTS	COLLECTOR MA
A	1000	-4	—
B	1000	—	-0.5
C	—	-4	-0.5





2N206

2N206

# JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For small-signal audio-frequency applications

## GENERAL DATA

Electrical, At Ambient Temperature of 25°C:

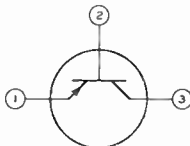
Maximum DC Collector Current for dc collector-to-base voltage of -30 volts with emitter open. . . . .	-10	μamp
Maximum DC Emitter Current for dc emitter-to-base voltage of -12 volts with collector open. . . . .	-10	μamp
Junction Temperature Rise (In free air). . .	0.3	°C/mw

### Mechanical:

Mounting Position. . . . .	Any
Maximum Length (Excluding flexible leads). . . . .	0.405"
Maximum Diameter . . . . .	0.240"
Case . . . . .	Metal, Insulated
Envelope Seals . . . . .	Hermetic
Leads, Flexible. . . . .	3
Length . . . . .	1.5" ± 0.015"
Orientation and diameter . . . . .	See Dimensional Outline

BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector  
(Adjacent to red dot on side of envelope)

## AUDIO-FREQUENCY AMPLIFIER -- Class A

Maximum Ratings, Absolute Values:

DC COLLECTOR-TO-BASE VOLTAGE . . . . .	-30 max.	volts
DC EMITTER-TO-BASE VOLTAGE . . . . .	-12 max.	volts
DC COLLECTOR CURRENT . . . . .	-50 max.	ma
DC EMITTER CURRENT . . . . .	50 max.	ma
COLLECTOR DISSIPATION (At ambient temperature of 25°C) . . . . .	75 max.	mw
AMBIENT TEMPERATURE (During operation) . . . . .	71 max.	°C
STORAGE-TEMPERATURE RANGE. . . . .	-65 to +85	°C

Characteristics, At Ambient Temperature of 25°C:

Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage. . . . .	-5	volts
DC Collector Current . . . . .	-1	ma
Power Gain: With load resistance = 20,000 ohms, and input resistance = 1200 ohms . . . . .	46	db
Noise Factor: Measured with a noise diode and thermo-couple voltmeter with load resistance		



2N206

## JUNCTION TRANSISTOR

= 20,000 ohms, generator resistance = 1000 ohms, and equivalent noise bandwidth = 12.3 kc with geometric mean of 300 cps. . . . . 9 db

**Small-Signal T Parameters:**\*

DC Collector-to-Emitter Voltage ( $V_{CE}$ ) . . . . .	-3	-5	volts
DC Collector Current ( $I_C$ ) . . . . .	-0.2	-1	ma
Emitter Resistance ( $r_e$ ) . . . . .	104	21	ohms
Base Resistance ( $r_b$ ) . . . . .	1270	580	ohms
Mutual Resistance ( $r_m$ ) . . . . .	3.25	1.78	megohms
Collector Resistance ( $r_c$ ) . . . . .	3.34	1.82	megohms
Current Transfer Ratio ( $\alpha_f$ ) <sup>■</sup> . . . . .	-33	-47	

**Small-Signal Hybrid- $\pi$  Parameters:**\*

DC Collector-to-Emitter Voltage ( $V_{CE}$ ) . . . . .	-3	-5	volts
DC Collector Current ( $I_C$ ) . . . . .	-0.2	-1	ma
Resistance $r_{bb'}$ . . . . .	210	200	ohms
Conductance $g_{b'e}$ . . . . .	225	710	$\mu$ hos
Conductance $g_{ce}$ . . . . .	2.3	7.6	$\mu$ hos
Conductance $g_{b'c}$ . . . . .	0.27	0.4	$\mu$ ho
Capacitance $C_{b'e}$ . . . . .	2380	9400	$\mu$ f
Capacitance $C_{b'c}$ . . . . .	48	35	$\mu$ f
Intrinsic Transconductance ( $g_m$ ) . . . . .	7430	33400	$\mu$ hos

*Common-Base Circuit, Emitter Input*

DC Collector-to-Base Voltage. . . . .	-3	-5	volts
DC Collector Current. . . . .	-0.2	-1	ma

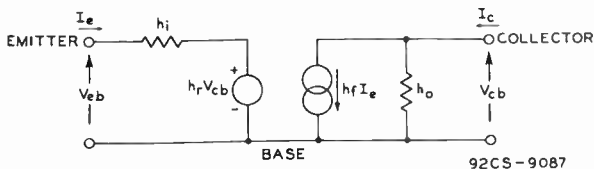
## Power Gain:

With load resistance = 0.5 megohm,  
and input resistance = 140 ohms. . . . . 35 db

Frequency at which the current transfer ratio drops to one-half the square root of two times its value at 1 kc. 620 780 kc

**Small-Signal H Parameters:**

*Derived from accompanying two-generator equivalent circuit, and applicable to that portion of the audio-frequency range in which internal capacitance effects may be neglected*



\* As derived from corresponding equivalent circuit shown under type 2N104.

■ Measured at 1 kc.



2N206

2N206

## JUNCTION TRANSISTOR

DC Collector-to-Base Voltage ( $V_{CB}$ ) . . . . .	-3	-5	volts
DC Collector Current ( $I_C$ ) . . . . .	-0.2	-1	ma
Input Resistance, output circuit shorted ( $h_i$ ) . . . . .	137	33	ohms
Reverse Voltage Transfer Ratio, input circuit open ( $h_r$ ) . . . . .	$3.8 \times 10^{-4}$	$3.2 \times 10^{-4}$	
Forward Current Transfer Ratio, output circuit shorted ( $h_f$ ) . . . . .	-0.974	-0.980	
Output Conductance, input circuit open ( $h_o$ ) . . . . .	0.3	0.55	$\mu\text{hos}$

*Common-Collector Circuit, Base Input*

DC Emitter-to-Collector Voltage . . . . .	$\bar{5}$		volts
DC Emitter Current . . . . .	0.2		ma
Power Gain:			
With load resistance = 18,000 ohms, and input resistance = 0.56 megohm . . . . .		30	db

## OPERATING CONSIDERATIONS

The 2N206 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of the 2N206 are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

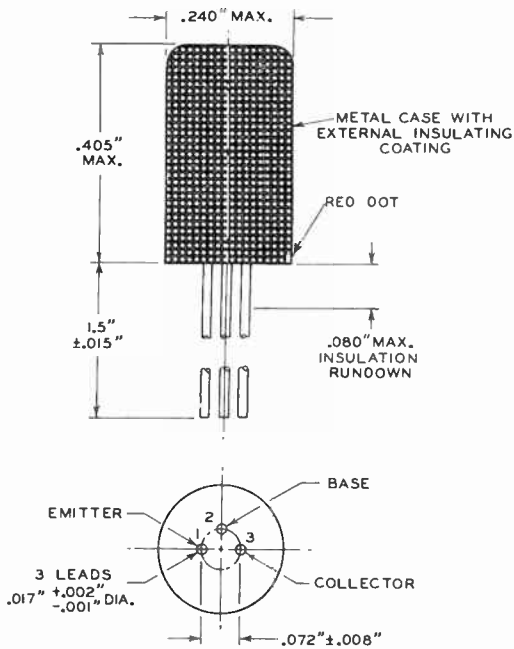
When dip soldering is employed in the assembly of printed circuitry using the 2N206, the temperature of the solder should not exceed 230°C for a maximum immersion period of 10 seconds.

2N206



2N206

# JUNCTION TRANSISTOR



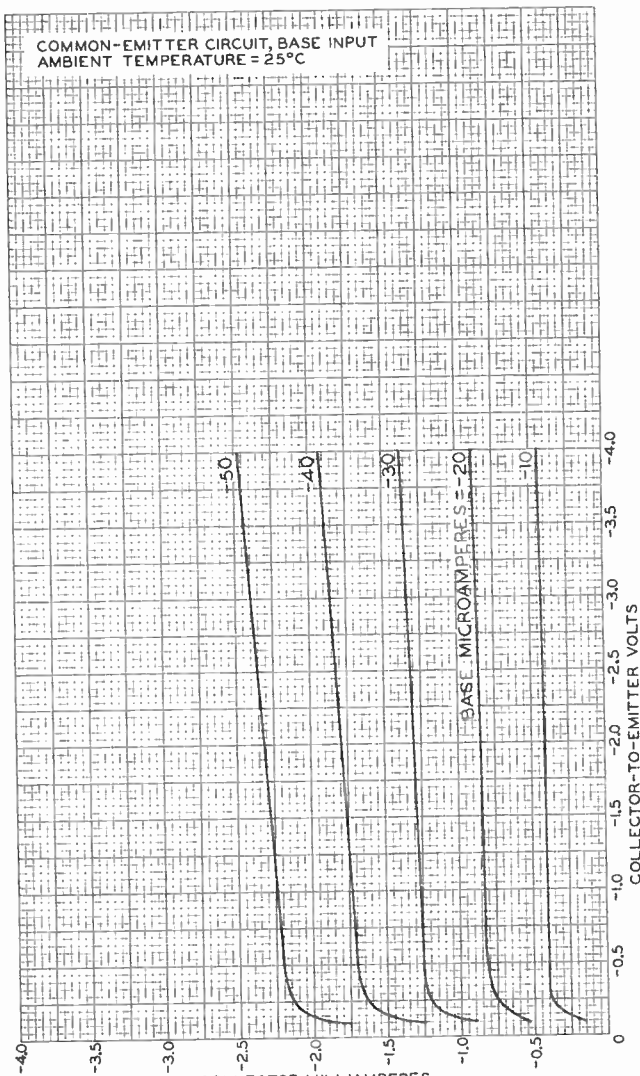
92CS-9025



2N206

2N206

### AVERAGE COLLECTOR CHARACTERISTICS



COLLECTOR MILLIAMPERES

SEMICONDUCTOR DIVISION

RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

92CM-9049

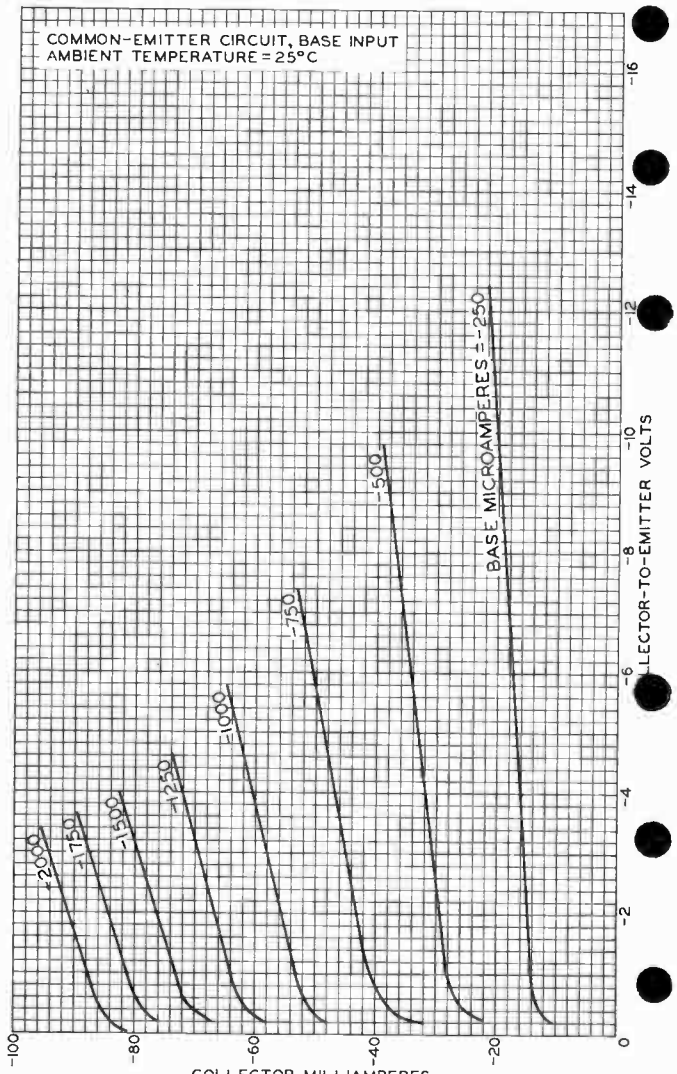
2N206



2N206

### AVERAGE COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE = 25°C



COLLECTOR MILLIAMPERES  
SEMICONDUCTOR DIVISION

RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

92CM-9050

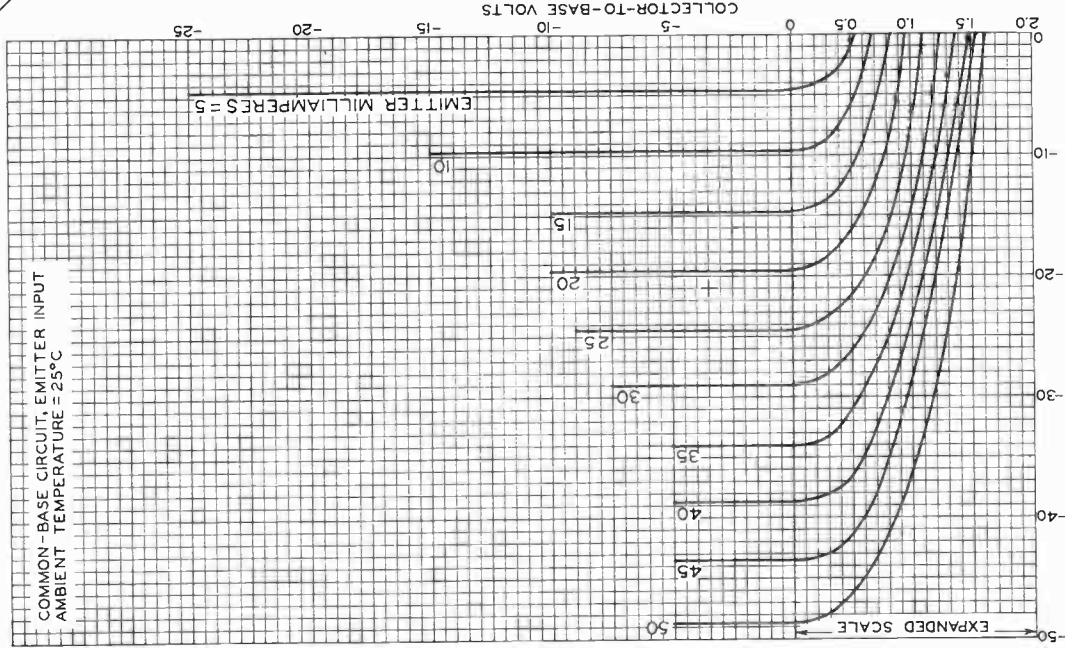




2N206

# AVERAGE COLLECTOR CHARACTERISTICS

COMMON-BASE CIRCUIT, EMITTER INPUT  
AMBIENT TEMPERATURE = 25°C



COLLECTOR MILLIAMPERES

SEMICONDUCTOR DIVISION

RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

92CM-9051

2N206





2N215

# JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

*For small-signal audio-frequency applications*

2N215

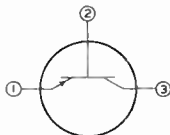
The 2N215 is the same as the 2N104 except for the following items:

### Mechanical:

- Maximum Length (Excluding flexible leads) . . . . . 0.455"
- Leads, Flexible. . . . . 3
- Length . . . . . 1.5" ± 0.015"
- Orientation and diameter . . . . . See Dimensional Outline

BOTTOM VIEW

Lead 1 - Emitter



Lead 3 - Collector  
(Adjacent to red dot on side of envelope)

Lead 2 - Base

### OPERATING CONSIDERATIONS

The 2N215 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The flexible leads of the 2N215 are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

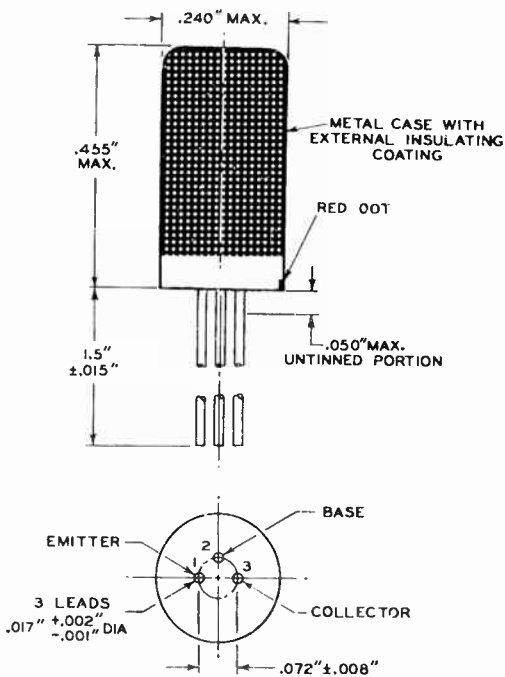
When dip soldering is employed in the assembly of printed circuitry using the 2N215, the temperature of the solder should not exceed 230°C for a maximum immersion period of 10 seconds.

2N215



2N215

# JUNCTION TRANSISTOR



92CS-9026



2N217

# 2N217

## JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For large-signal audio-frequency applications

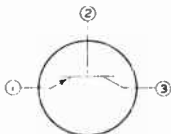
The 2N217 is the same as the 2N109 except for the following items:

### Mechanical:

Maximum Length (Excluding flexible leads) . . . . .	0.405"
Leads, Flexible . . . . .	3
Length . . . . .	1.5" ± 0.015"
Orientation and diameter . . . . .	See Dimensional Outline

BOTTOM VIEW

Lead 1 - Emitter



Lead 3 - Collector  
(Adjacent to red dot on side of envelope)

Lead 2 - Base

### OPERATING CONSIDERATIONS

The 2N217 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The flexible leads of the 2N217 are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

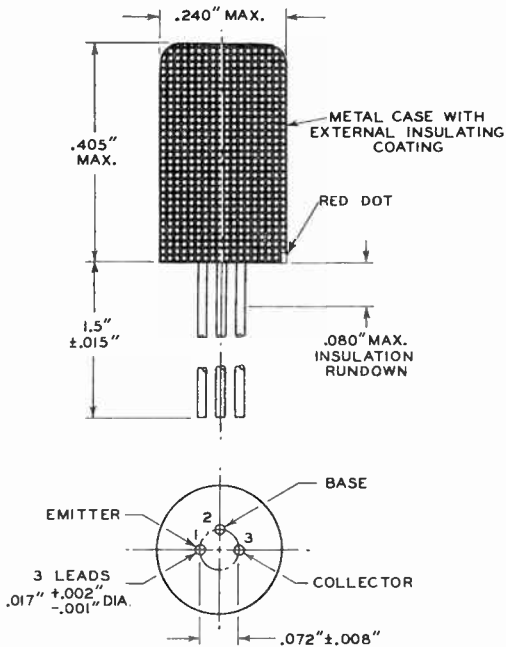
When dip soldering is employed in the assembly of printed circuitry using the 2N217, the temperature of the solder should not exceed 230°C for a maximum immersion period of 10 seconds.

2N217



2N217

# JUNCTION TRANSISTOR



92CS-9025



2N218

# JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For 455-kc intermediate-frequency applications

2N218

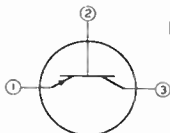
The 2N218 is the same as the 2N139 except for the following items:

### Mechanical:

Maximum Length (Excluding flexible leads) . . . . .	0.405"
Leads, Flexible . . . . .	3
Length . . . . .	1.5" ± 0.015"
Orientation and diameter . . . . .	See Dimensional Outline

BOTTOM VIEW

Lead 1 - Emitter



Lead 3 - Collector  
(Adjacent to red dot on side of envelope)

Lead 2 - Base

### OPERATING CONSIDERATIONS

The 2N218 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

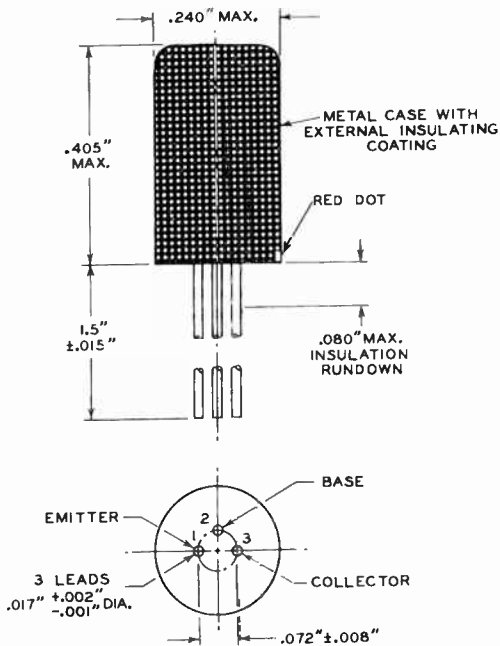
The flexible leads of the 2N218 are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using the 2N218, the temperature of the solder should not exceed 230°C for a maximum immersion period of 10 seconds.

2N218



# 2N218 JUNCTION TRANSISTOR



92CS-9025





2N219

2N219

# JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For 540 to 1600 kc converter applications

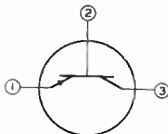
The 2N219 is the same as the 2N140 except for the following items:

### Mechanical:

Maximum Length (Excluding flexible leads) . . . . .	0.405"
Leads, Flexible . . . . .	3
Length . . . . .	1.5" ± 0.015"
Orientation and diameter . . . . .	See Dimensional Outline

BOTTOM VIEW

Lead 1 - Emitter



Lead 3 - Collector  
(Adjacent to red dot on side of envelope)

Lead 2 - Base

### OPERATING CONSIDERATIONS

The 2N219 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The flexible leads of the 2N219 are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

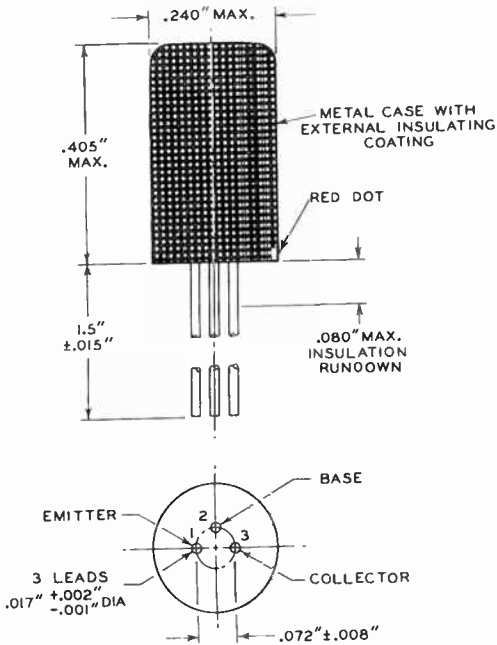
When dip soldering is employed in the assembly of printed circuitry using the 2N219, the temperature of the solder should not exceed 230°C for a maximum immersion period of 10 seconds.

2N219



2N219

# JUNCTION TRANSISTOR



92CS-9025



2N220

# JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

*For low-noise audio-frequency applications*

2N220

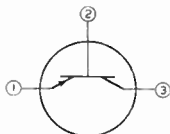
The 2N220 is the same as the 2N175 except for the following items:

### Mechanical:

- Maximum Length (Excluding flexible leads) . . . . . 0.405"
- Leads, Flexible . . . . . 3
- Length . . . . . 1.5" ± 0.015"
- Orientation and diameter . . . . . See Dimensional Outline

BOTTOM VIEW

Lead 1 - Emitter



Lead 3 - Collector  
(Adjacent to red dot on side of envelope)

Lead 2 - Base

### OPERATING CONSIDERATIONS

The 2N220 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

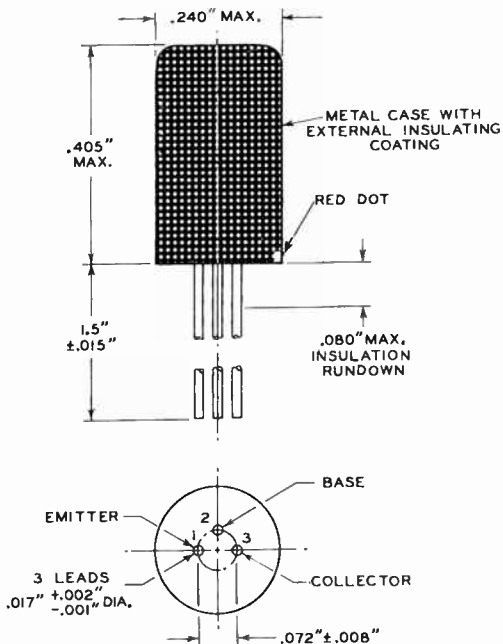
The flexible leads of the 2N220 are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using the 2N220, the temperature of the solder should not exceed 230°C for a maximum immersion period of 10 seconds.

2N220



# 2N220 JUNCTION TRANSISTOR



92CS-9025



2N247

# 2N247

## DRIFT TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For radio-frequency amplifier applications

### GENERAL DATA

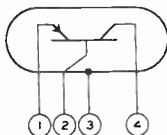
Electrical, At Ambient Temperature of 25°C:

Minimum DC Collector-to-Base Voltage for dc collector current of -50 $\mu$ amp with emitter open. . . . .	-40	volts
Maximum DC Collector Current for dc collector-to-base voltage of -1 volt with emitter open. . . . .	-10	$\mu$ amp
Maximum DC Collector Current for dc collector-to-base voltage of -30 volts with emitter open. . . . .	-16	$\mu$ amp
Minimum DC Emitter-to-Base Voltage for dc emitter current of -50 $\mu$ amp with collector open. . . . .	-1	volt

### Mechanical:

Mounting Position. . . . .	Any
Maximum Length (Excluding flexible leads). . . . .	0.375"
Maximum Diameter . . . . .	0.360"
Case . . . . .	Metal, Insulated
Envelope Seals . . . . .	Hermetic
Leads, Flexible. . . . .	4
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See Dimensional Outline

Lead 1 - Emitter



Lead 2 - Base

Lead 3 - Interlead  
Shield,  
Metal  
Case  
Lead 4 - Collector

### RADIO-FREQUENCY AMPLIFIER -- Class A

Maximum Ratings, Absolute Values:

DC COLLECTOR-TO-BASE VOLTAGE . . . . .	-35 max.	volts
DC EMITTER-TO-BASE VOLTAGE . . . . .	-1 max.	volt
DC COLLECTOR CURRENT . . . . .	-10 max.	ma
DC EMITTER CURRENT . . . . .	10 max.	ma
COLLECTOR DISSIPATION (At ambient temperatures up to 71°C) . . . . .	35 max.	mw
AMBIENT TEMPERATURE (During operation) . . . . .	71 max.	°C
STORAGE-TEMPERATURE RANGE. . . . .	-55 to +85	°C

Characteristics, At Ambient Temperature of 25°C:

Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage. . . . .	-9	volts
DC Collector Current . . . . .	-1	ma
Current Transfer Ratio ( $\alpha_f$ ) <sup>■</sup> . . . . .	-60	

■: See next page.

2N247



2N247

## DRIFT TRANSISTOR

Small-Signal Hybrid- $\pi$  Parameters:<sup>a</sup>

DC Collector-to-Emitter Voltage ( $V_{CE}$ ) . . . . .	-9	volts
DC Collector Current ( $I_C$ ) . . . . .	-1	ma
Resistance $r_{bb'}$ . . . . .	40	ohms
Conductance $g_{b'e}$ . . . . .	640	$\mu$ hos
Conductance $g_{ce}$ (Approx.) . . . . .	0	$\mu$ hos
Conductance $g_{b'c}$ (Approx.) . . . . .	0	$\mu$ hos
Capacitance $C_{b'e}$ . . . . .	200	$\mu$ f
Capacitance $C_{b'c}$ . . . . .	1.7	$\mu$ f
Interlead Capacitance between collector and base leads with interlead shield connected to ground and all leads cut to 5/16" . . . . .	0.003	$\mu$ f
Intrinsic Transconductance ( $g_m$ ) . . . . .	37000	$\mu$ hos
Frequency <sup>b</sup> for unity power amplification.	132	Mc

## Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage . . . . .	-9	volts
DC Collector Current . . . . .	-1	ma
Current Transfer Ratio ( $\alpha_f$ ) <sup>a</sup> . . . . .	0.984	
Frequency at which the current transfer ratio drops to one-half the square root of two times its value at 1 kc. . . . .	30	Mc

## Typical Operation, At Ambient Temperature of 25°C:

## Common-Emitter Circuit, Base Input

At frequency of	1.5	10.7	Mc
DC Collector-to-Emitter Voltage . . . . .	-9	-9	volts
DC Collector Current . . . . .	-1	-1	ma
DC Base-to-Emitter Voltage . . . . .	-0.2	-0.2	volt
Input Resistance, output circuit shorted. . . . .	1350	170	ohms
Output Resistance, input circuit shorted. . . . .	70000	4500	ohms
Power Gain <sup>a</sup> . . . . .	45	24	db

\* As derived from corresponding equivalent circuit shown under type 2N104.

<sup>b</sup> This frequency (figure of merit) may be calculated from the equation

$$f = \frac{1}{4\pi} \sqrt{\frac{g_m}{r_{bb'} \cdot C_{b'c} \cdot C_{b'e}}}$$

<sup>a</sup> Measured at 1 kc.

<sup>b</sup> Measured in a single-tuned unilateralized circuit matched to the generator and load impedances for maximum transfer of power. Transformer insertion losses not included.

## OPERATING CONSIDERATIONS

The 2N247 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.



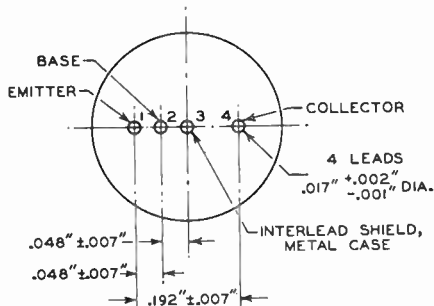
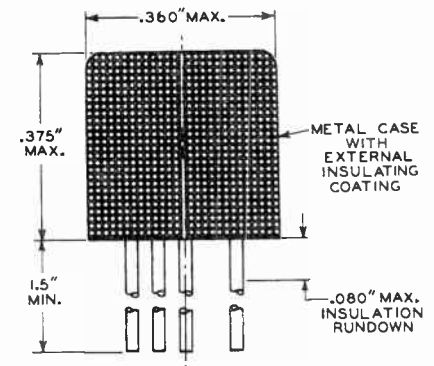
2N247

2N247

# DRIFT TRANSISTOR

The *flexible leads* of the 2N247 are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using the 2N247, the temperature of the solder should not exceed 230°C for a maximum immersion period of 10 seconds.



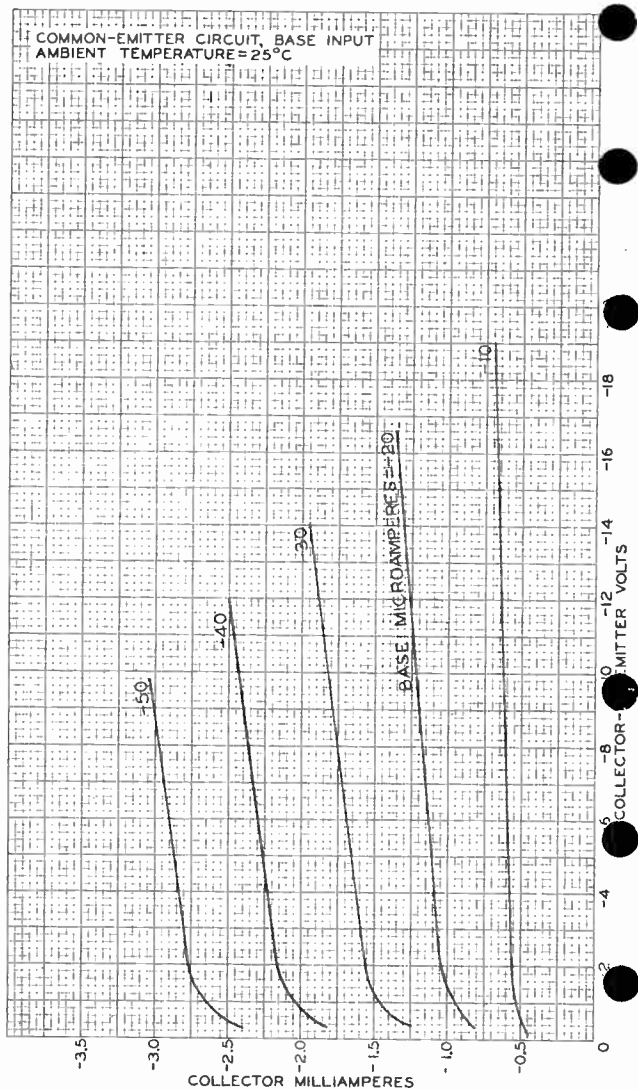
92CS-9122R1

2N247



2N247

## AVERAGE COLLECTOR CHARACTERISTICS



SEMICONDUCTOR DIVISION

RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

92CM-9107

World Radio History

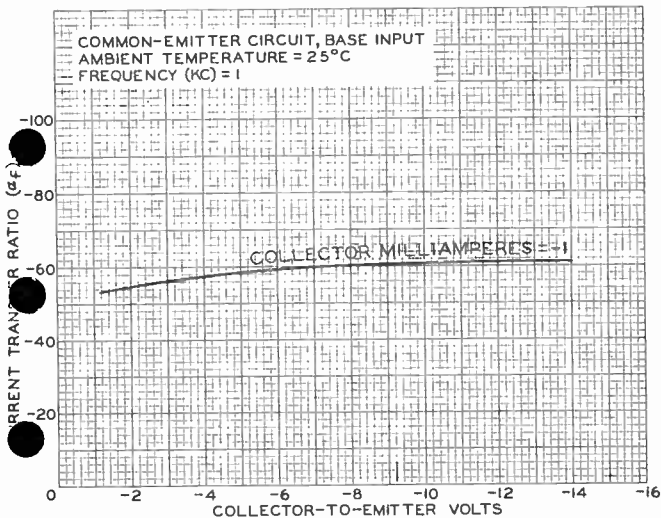
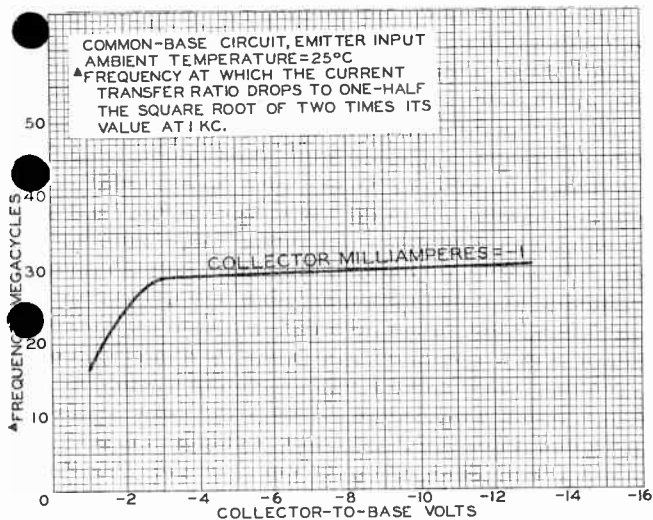




2N247

2N247

### AVERAGE CHARACTERISTICS

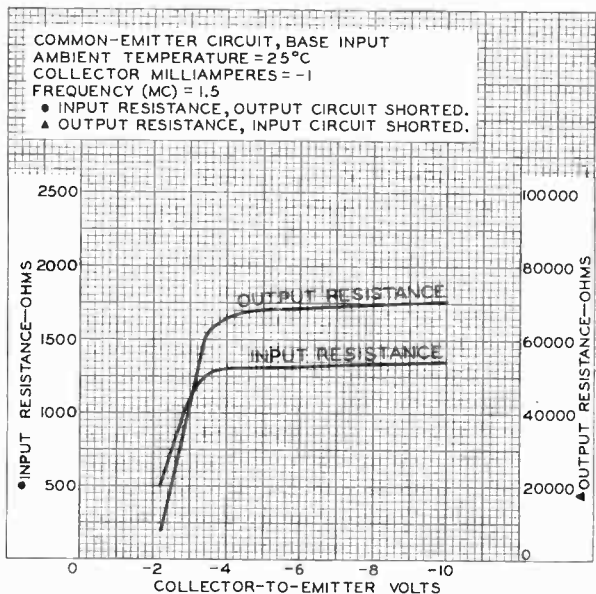
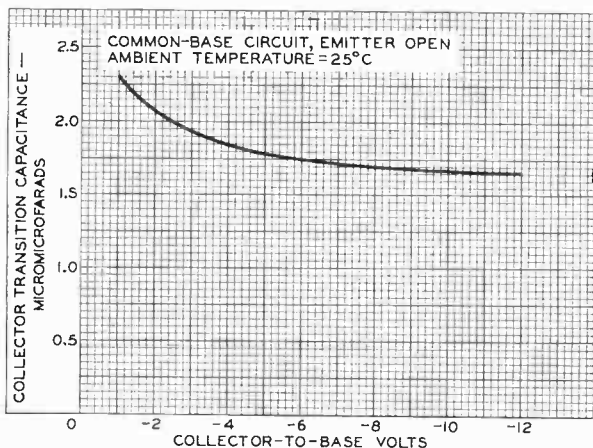


2N247



2N247

## AVERAGE CHARACTERISTICS



## Transistor

GERMANIUM P-N-P ALLOY-JUNCTION TYPE  
For Computer Switching Applications

## GENERAL DATA

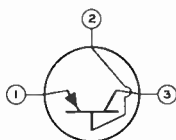
## Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.410"
Maximum Diameter . . . . .	0.240"
Dimensional Outline . . . . .	JEDEC No. TO-1
Case . . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	

BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base



Lead 3 - Collector  
(Adjacent  
to red dot  
on side of  
case)

## SWITCHING SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values:*

COLLECTOR-TO-BASE VOLTAGE . . . . .	-25 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With dc emitter-to-base volts = -1 . . . . .	-24 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-12 max.	volts
COLLECTOR CURRENT . . . . .	-100 max.	ma
EMITTER CURRENT . . . . .	100 max.	ma
TRANSISTOR DISSIPATION: <sup>a</sup>		
At ambient temperature of 25° C or below . . . . .	120 max.	mw
At ambient temperature of 55° C . . . . .	35 max.	mw
At ambient temperature of 71° C . . . . .	10 max.	mw
AMBIENT-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +85	°C
LEAD TEMPERATURE:		
For 10 seconds maximum . . . . .	255 max.	°C

ELECTRICAL CHARACTERISTICS  
and

## OPERATING CONSIDERATIONS

shown under Type 2N404 also apply to the 2N269

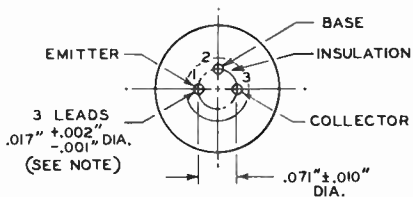
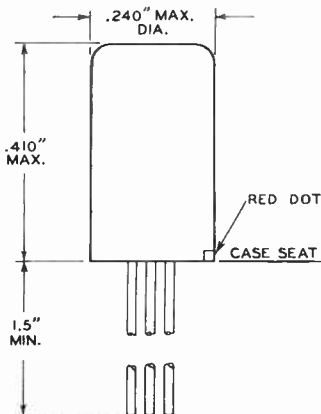
<sup>a</sup> See accompanying *Rating Chart* and also *Transistor-Dissipation Rating Chart* in General Section.

← Indicates a change.



# 2N269

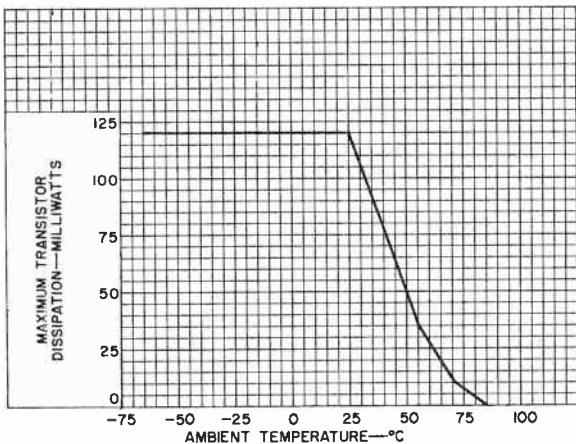
JEDEC No. T0-1



92CS-9148R6

NOTE: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE CASE SEAT. BETWEEN 0.25" AND 1.5", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

## RATING CHART



92CS-10908RI







2N269

# 2N269

## JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For "on-off" control applications

### GENERAL DATA

#### Electrical:

Minimum DC Collector-to-Base Voltage for dc collector current of $-20 \mu\text{a}$ with emitter open, and at ambient temperature of $25^\circ\text{C}$ .	-25	volts
Minimum DC Emitter-to-Base Voltage for dc emitter current of $-20 \mu\text{a}$ with collector open, and at ambient temperature of $25^\circ\text{C}$ .	-12	volts
Maximum DC Emitter-to-Base Voltage for dc collector-to-base voltage of $-20$ volts, emitter load resistance of 11 megohms, emitter-to-base supply voltage of 0 volts, and at ambient temperature of $25^\circ\text{C}$ .	-1	volt
Maximum DC Collector Current for dc collector-to-base voltage of $-2.5$ volts with emitter open, and at ambient temperature of:		
$25^\circ\text{C}$	-2.5	$\mu\text{a}$
$80^\circ\text{C}$	-50	$\mu\text{a}$
Maximum DC Collector Current for dc collector-to-base voltage of $-12$ volts with emitter open, and at ambient temperature of:		
$25^\circ\text{C}$	-4	$\mu\text{a}$
$80^\circ\text{C}$	-60	$\mu\text{a}$
Maximum DC Emitter Current for dc emitter-to-base voltage of $-2.5$ volts with collector open, and at ambient temperature of:		
$25^\circ\text{C}$	-2.5	$\mu\text{a}$
$80^\circ\text{C}$	-50	$\mu\text{a}$
Maximum Junction-Temperature Rise (With transistor in free air)	0.35	$^\circ\text{C}/\text{mw}$
Minimum Junction-Temperature Change which will cause collector current to double with dc collector-to-base voltage equal to or greater than $-2.5$ volts with emitter open.	10	$^\circ\text{C}$
Maximum Collector-to-Base Capacitance for dc collector-to-base voltage of $-6$ volts with emitter open, and at ambient temperature of $25^\circ\text{C}$ .	20	$\mu\text{mf}$

#### Mechanical:

Mourting Position	Any
Maximum Length (Excluding flexible leads)	0.405"
Maximum Diameter	0.240"

2N269



2N269

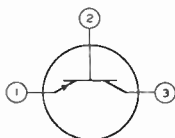
## JUNCTION TRANSISTOR

Case . . . . .	Metal, Insulated
Envelope Seals . . . . .	Hermetic
Leads, Flexible. . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See Dimensional Outline

BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base



Lead 3 - Collector  
(Adjacent  
to red dot  
on side of  
envelope)

## LOW-LEVEL SWITCHING SERVICE

## Maximum Ratings, Absolute Values:

PEAK COLLECTOR-TO-BASE VOLTAGE . . . . .	-25 max.	volts
DC COLLECTOR-TO-BASE VOLTAGE . . . . .	-20 max.	volts
PEAK EMITTER-TO-BASE VOLTAGE . . . . .	-12 max.	volts
DC EMITTER-TO-BASE VOLTAGE . . . . .	-9 max.	volts
COLLECTOR CURRENT (DC or Peak) . . . . .	-100 max.	ma
EMITTER CURRENT (DC or Peak) . . . . .	100 max.	ma
TRANSISTOR DISSIPATION:*		
At ambient temperatures up to 55 °C. . . . .	35 max.	mW
At ambient temperature of 71 °C. . . . .	10 max.	mW
AMBIENT TEMPERATURE (During operation) . . . . .	71 max.	°C
STORAGE-TEMPERATURE RANGE. . . . .	-65 to +85	°C

## Characteristics, At Ambient Temperature of 25 °C:

## Common-Emitter Circuit, Base Input

DC Collector Current . . . . .	-12	-24	ma
DC Base Current. . . . .	-0.342	-0.858	ma
Maximum DC Collector-			
to-Emitter Voltage . . . . .	-0.15	-0.2	volt
Maximum DC Base-			
to-Emitter Voltage . . . . .	-0.35	-0.4	volt

## Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage . . . . .	-6	volts
DC Emitter Current . . . . .	1	ma
Minimum Frequency at which the current transfer ratio is 0.707 (or $1/\sqrt{2}$ ) of its value at 1 kc. . . . .	4	Mc

\* The maximum transistor-dissipation rating is reduced 1.56 milliwatts for each degree centigrade the ambient temperature is increased above 55 °C.





2N269

2N269

## JUNCTION TRANSISTOR

### OPERATING CONSIDERATIONS

The 2N269 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of the 2N269 are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using the 2N269, the temperature of the solder should not exceed 230 °C for a maximum immersion period of 10 seconds.

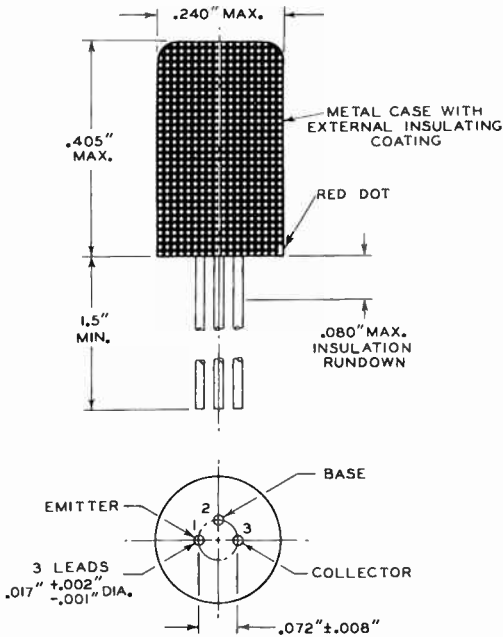
The accompanying curves may be used to determine the typical maximum (or minimum) value of one transistor parameter when two other transistor parameters are known. For example, using the BASE CHARACTERISTIC curve, if a base-to-emitter voltage of -0.35 volt (A) is applied to the 2N269 with the collector-to-base voltage equal to 0, a typical minimum base-current value of -1.25 milliamperes (a) will be obtained. Similarly, for a base current of -4 milliamperes (B) flowing through the base circuit with the collector-to-base voltage equal to 0, a typical maximum base-to-emitter-voltage value of -0.45 (b) will be obtained.

2N269



2N269

# JUNCTION TRANSISTOR



92CS-9147

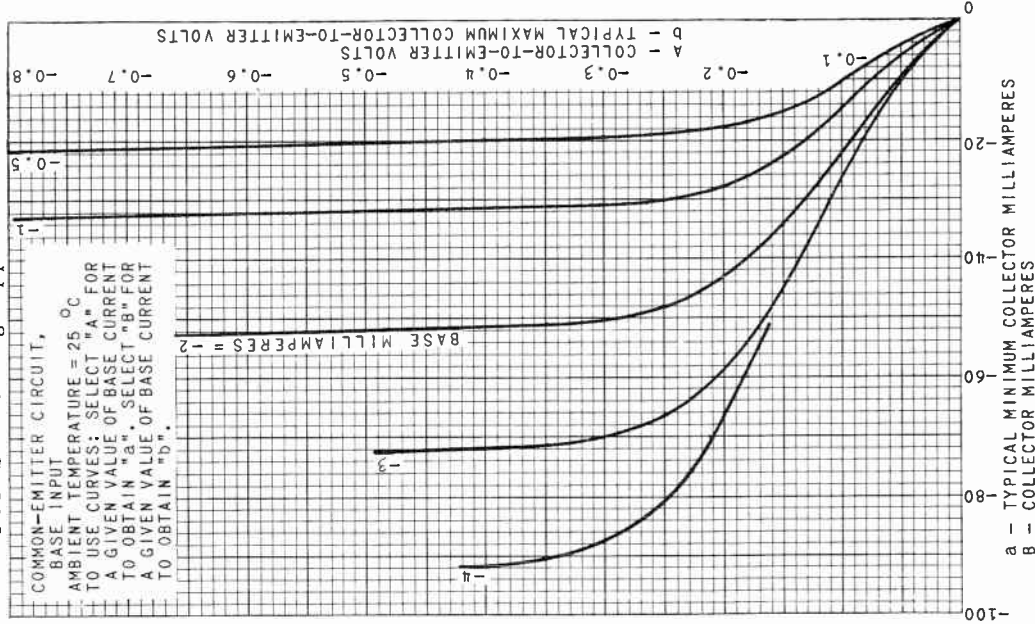


2N269

2N269

# COLLECTOR CHARACTERISTICS

For Switching Applications



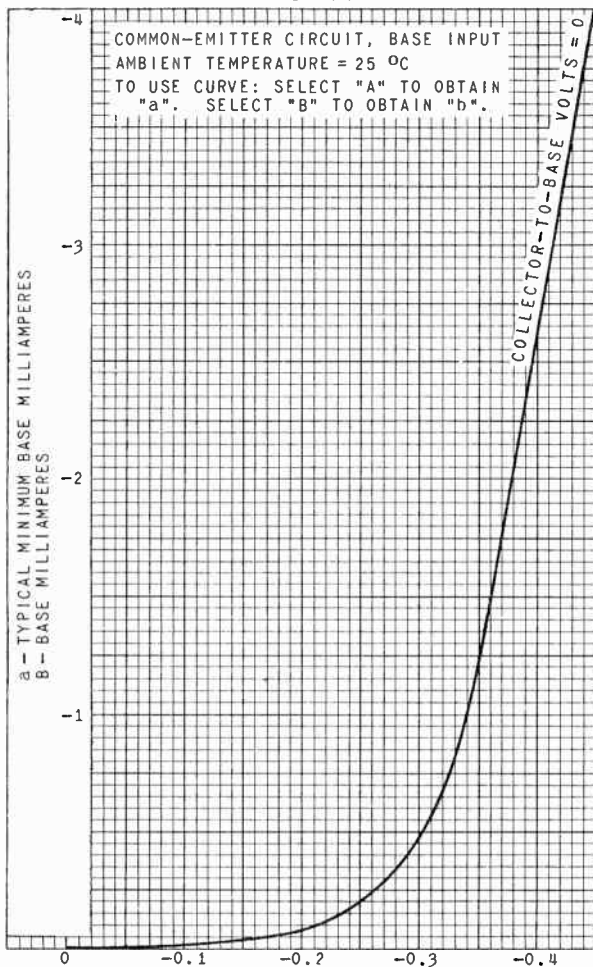
2N269



2N269

# BASE CHARACTERISTIC

For Switching Applications



A - BASE-TO-EMITTER VOLTS  
 B - TYPICAL MAXIMUM BASE-TO-EMITTER VOLTS



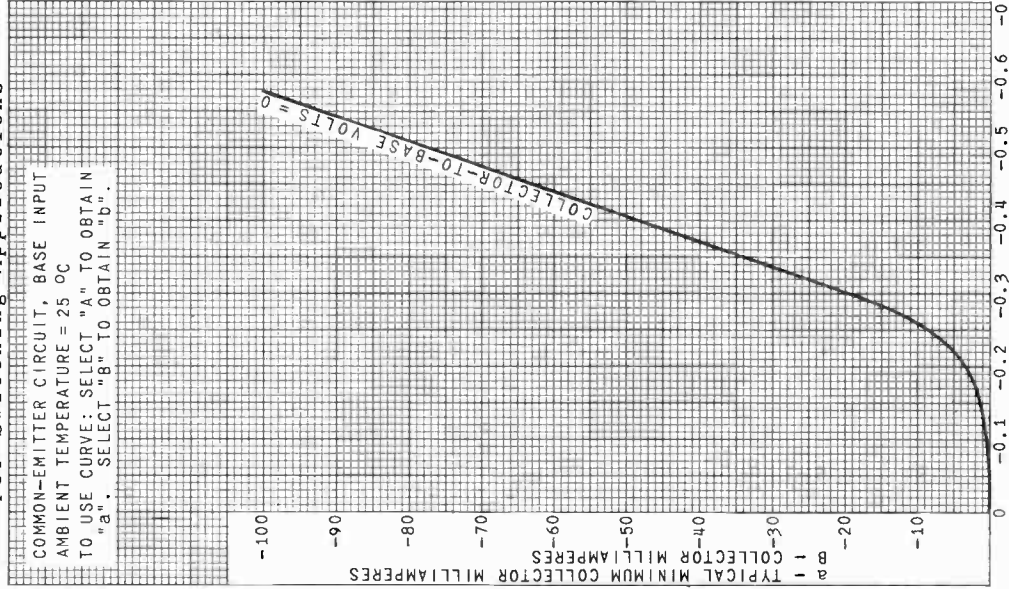
2N269

2N269

# TRANSFER CHARACTERISTIC

For Switching Applications

COMMON-EMITTER CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE = 25 °C  
TO USE CURVE: SELECT "A" TO OBTAIN  
"a". SELECT "B" TO OBTAIN "b".



A - BASE-TO-EMITTER VOLTS  
B - TYPICAL MAXIMUM BASE-TO-EMITTER VOLTS

2N269

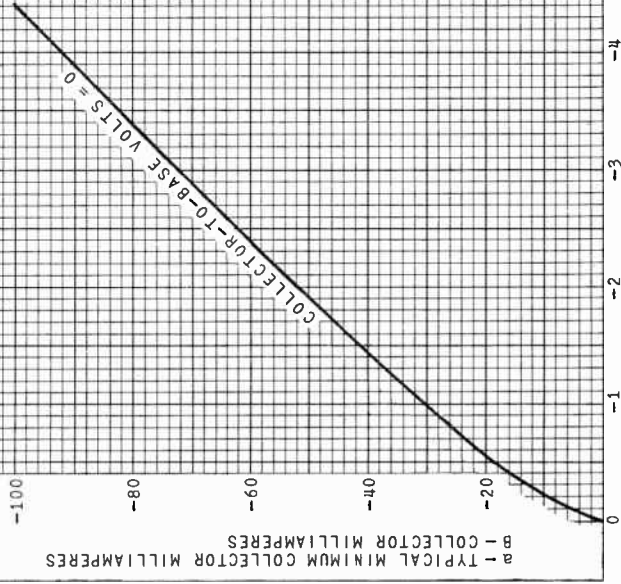


2N269

# CURRENT-TRANSFER CHARACTERISTIC

For Switching Applications

COMMON-EMITTER CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE = 25 °C  
TO USE CURVE: SELECT "A" TO OBTAIN  
"a". SELECT "B" TO OBTAIN "b".



B - TYPICAL MINIMUM COLLECTOR MILLIAMPERES

A - BASE MILLIAMPERES  
b - TYPICAL MAXIMUM BASE MILLIAMPERES



2N270

# 2N270

## JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For large-signal audio-frequency applications

### GENERAL DATA

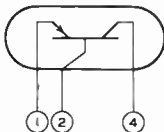
#### Electrical:

Maximum DC Collector Current for dc collector-to-base voltage of -25 volts with emitter open, and at ambient temperature of 25 °C. . . . .	-10	μa
Maximum DC Emitter Current for dc emitter-to-base voltage of -12 volts with collector open, and at ambient temperature of 25 °C. . . . .	-10	μa
Maximum Junction-Temperature Rise (With transistor in free air) . . . . .	0.24	°C/mw

#### Mechanical:

Mounting Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.375"
Maximum Diameter. . . . .	0.360"
Case. . . . .	Metal, Insulated
Envelope Seals. . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length. . . . .	1.5"
Orientation and diameter. . . . .	See Dimensional Outline

Lead 1 - Emitter



Lead 4 - Collector

Lead 2 - Base

### AUDIO-FREQUENCY AMPLIFIER -- Class A

#### Maximum Ratings, Absolute Values:

PEAK COLLECTOR-TO-BASE VOLTAGE. . . . .	-25 max.	volts
DC COLLECTOR-TO-BASE VOLTAGE (For inductive load) . . . . .	-12 max.	volts
PEAK COLLECTOR CURRENT. . . . .	-150 max.	ma
DC COLLECTOR CURRENT. . . . .	-75 max.	ma
PEAK EMITTER CURRENT. . . . .	150 max.	ma
DC EMITTER CURRENT. . . . .	75 max.	ma
COLLECTOR DISSIPATION (At ambient temperatures up to 50 °C) . . . . .	150 max.	mw
AMBIENT TEMPERATURE (During operation). . . . .	50 max.	°C
STORAGE-TEMPERATURE RANGE . . . . .	-65 to +85	°C

#### Characteristics, At Ambient Temperature of 25 °C:

Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage . . . . .	-1	volt
DC Collector Current. . . . .	-150	ma
Large-Signal DC Current Transfer Ratio. . . . .	70	

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2N270

## JUNCTION TRANSISTOR

Typical Operation, At Ambient Temperature of 25 °C:

Common-Emitter Circuit, Base Input

DC Supply Voltage . . . . .	9	volts
Emitter Resistor. . . . .	100	ohms
Emitter Bypass Capacitor. . . . .	50	μf
DC Collector Current. . . . .	-19	ma
DC Base-to-Emitter Voltage. . . . .	-0.19	volt
Input Resistance. . . . .	400	ohms
Load Impedance. . . . .	400	ohms
Signal Frequency. . . . .	1	kc
Power Gain♦ . . . . .	35	db
Total Harmonic Distortion . . . . .	10 <sup>▲</sup>	max. %
Max.-Signal Power Output♦ . . . . .	60	mW

## AUDIO-FREQUENCY AMPLIFIER -- Class B

Maximum Ratings, Absolute Values:

PEAK COLLECTOR-TO-BASE VOLTAGE. . . . .	-20	max.	volts
DC COLLECTOR-TO-BASE VOLTAGE (For inductive load) . . . . .	-12	max.	volts
PEAK COLLECTOR CURRENT. . . . .	-150	max.	ma
DC COLLECTOR CURRENT. . . . .	-75	max.	ma
PEAK EMITTER CURRENT. . . . .	150	max.	ma
DC EMITTER CURRENT. . . . .	75	max.	ma
COLLECTOR DISSIPATION (At ambient temperatures up to 50 °C) . . . . .	150	max.	mW
AMBIENT TEMPERATURE (During operation). . . . .	50	max.	°C
STORAGE-TEMPERATURE RANGE . . . . .	-65 to +8°		°C

Characteristics, At Ambient Temperature of 25 °C:

Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage . . . . .	-1	volt
DC Collector Current. . . . .	-150	ma
Large-Signal DC Current Transfer Ratio. . . . .	70	

Typical Push-Pull Operation, At Ambient Temperature of 25 °C:

Common-Emitter Circuit, Base Input

Unless otherwise specified, values are for 2 transistors

DC Supply Voltage . . . . .	12	volts
Emitter Resistor. . . . .	5	ohms
DC Base-to-Emitter Voltage (Zero signal). . . . .	-0.11	volt
Peak Collector Current (Per transistor) . . . . .	-110	ma
Zero-Signal DC Collector Current (Per transistor) . . . . .	-2	ma
Max.-Signal DC Collector Current (Per transistor) . . . . .	-35	ma
Signal-Source Impedance (Base to base) . . . . .	4000	ohms

▲ This value is 4 per cent maximum at max.-signal power output of 10 milliwatts.

♦: See next page.





2N270

2N270

## JUNCTION TRANSISTOR

Load Impedance (Collector to collector) . . . . .	600	ohms
Signal Frequency . . . . .	1	kc
Circuit Efficiency . . . . .	75	%
Power Gain $\blacklozenge$ . . . . .	32	db
Total Harmonic Distortion . . . . .	10 <sup>■</sup> max.	%
Max.-Signal Power Output $\blacklozenge$ . . . . .	500	mw

$\blacklozenge$  Measured at the primary of the output transformer.

<sup>■</sup> This value is 5 per cent maximum at max.-signal power output of 10 milliwatts.

## OPERATING CONSIDERATIONS

The 2N270 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of the 2N270 are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using the 2N270, the temperature of the solder should not exceed 230 °C for a maximum immersion period of 10 seconds.

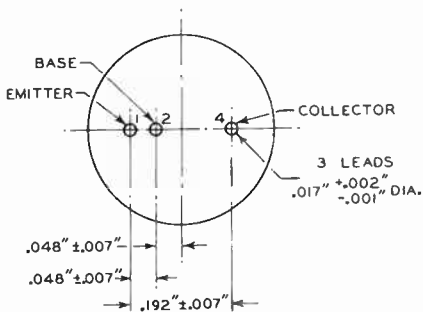
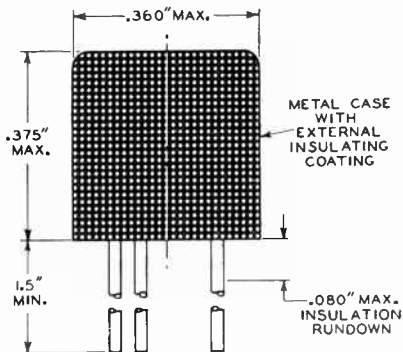
In *class B service*, when the 2N270 is operated at ambient temperatures other than 25 °C, the base-to-emitter voltage should be reduced or increased by approximately 0.002 volt for each degree the ambient temperature is above or below 25 °C, respectively. When this transistor is operated under varying ambient temperatures, some form of temperature compensation may be used in the base-to-emitter circuit to hold the operating point constant.

2N270



2N270

# JUNCTION TRANSISTOR



92CS-9176R1

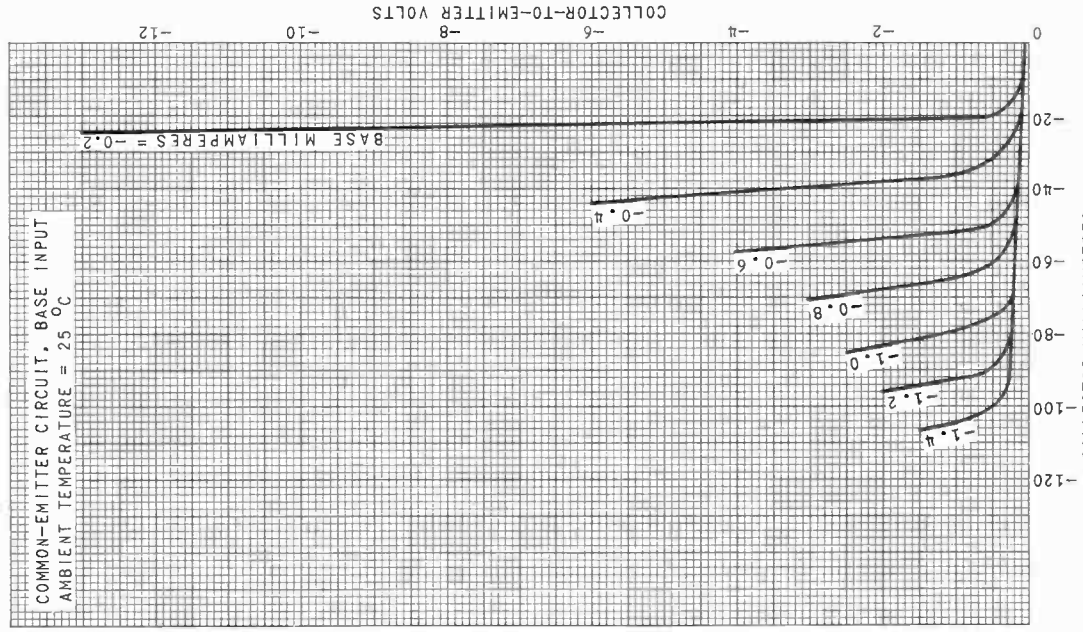


2N270

2N270

# AVERAGE COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE = 25 °C



COLLECTOR MILLIAMPERES

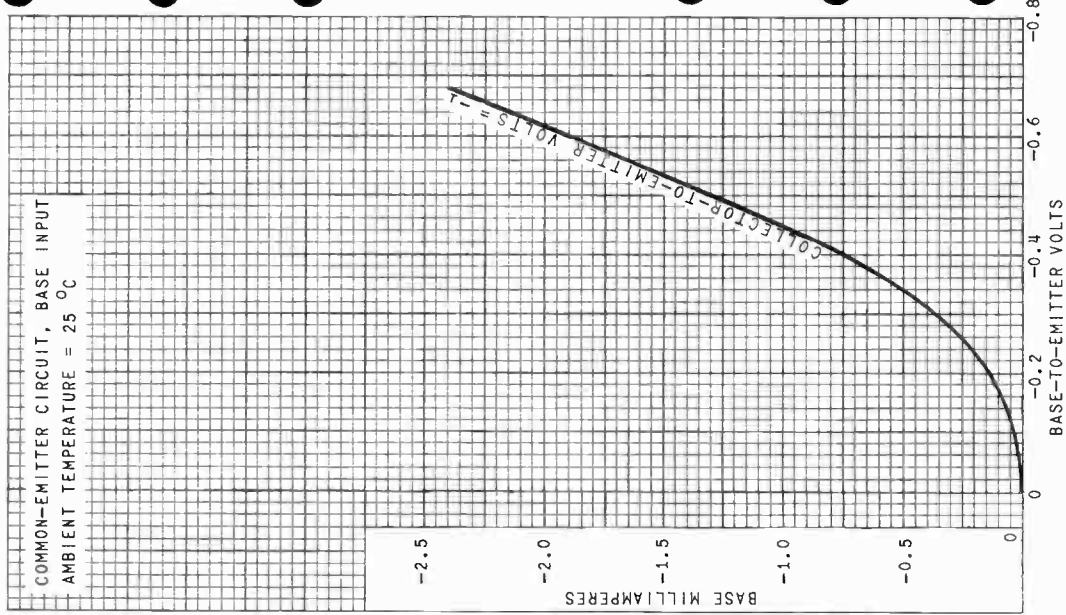
2N270



2N270

# AVERAGE BASE CHARACTERISTIC

COMMON-EMITTER CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE = 25 °C

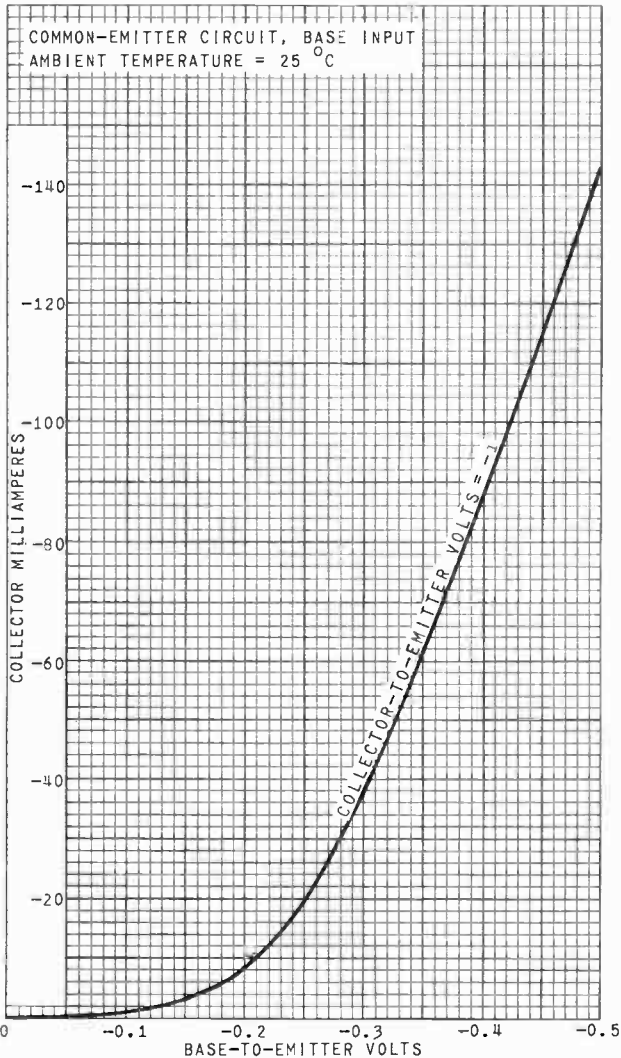




2N270

2N270

# AVERAGE TRANSFER CHARACTERISTIC



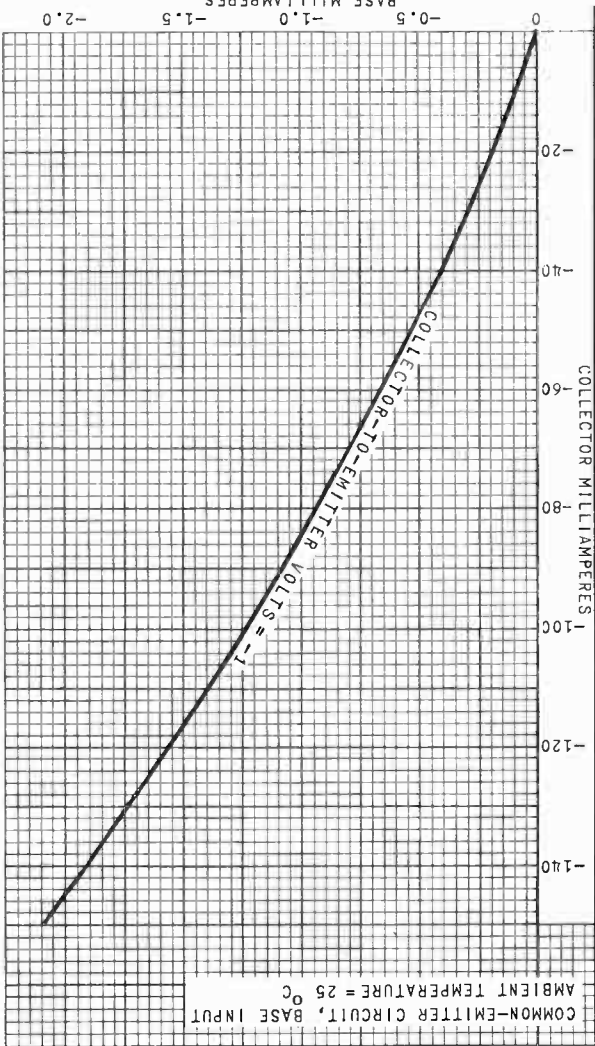
# AVERAGE CURRENT-TRANSFER CHARACTERISTIC

2N270



World Radio History

2N270





2N274

2N274

## DRIFT TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For radio-frequency amplifier applications

## GENERAL DATA

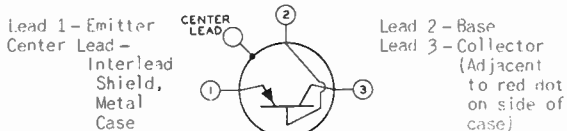
Electrical, At Ambient Temperature of 25° C:

Minimum DC Collector-to-Base Voltage for dc collector current of $-50 \mu\text{a}$ with emitter open. . . . .	-40	volts
Maximum DC Collector Current for dc collector-to-base voltage of $-1$ volt with emitter open. . . . .	$-10$	$\mu\text{a}$
Maximum DC Collector Current for dc collector-to-base voltage of $-12$ volts with emitter open. . . . .	$-16$	$\mu\text{a}$
Minimum DC Emitter-to-Base Voltage for dc emitter current of $-50$ $\mu\text{a}$ with collector open. . . . .	$-0.5$	volt

## Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads). . . . .	0.405"
Maximum Diameter . . . . .	0.240"
Case . . . . .	Metal
Envelope Seals . . . . .	Hermetic
Leads, Flexible. . . . .	4
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See Dimensional Outline

## BOTTOM VIEW



## RADIO-FREQUENCY AMPLIFIER — Class A

Maximum Ratings, Absolute Values:

DC COLLECTOR-TO-BASE VOLTAGE . . . . .	$-35$ max.	volts
DC EMITTER-TO-BASE VOLTAGE. . . . .	$-0.5$ max.	volt
DC COLLECTOR CURRENT . . . . .	$-10$ max.	ma
DC EMITTER CURRENT . . . . .	$10$ max.	ma
COLLECTOR DISSIPATION (At ambient temperatures up to 71° C). . . . .	$35$ max.	mw
AMBIENT TEMPERATURE (During operation) . . . . .	$71$ max.	°C
STORAGE-TEMPERATURE RANGE. . . . .	$-65$ to $+85$	°C

Characteristics, At Ambient Temperature of 25° C:

Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage. . . . .	$-9$	volts
DC Emitter Current . . . . .	$1$	ma
Forward Current Transfer Ratio <sup>■</sup> . . . . .	$-60$	

■: See next page.

2N274



2N274

## DRIFT TRANSISTOR

Small-Signal Hybrid- $\pi$  Parameters: \*

DC Collector-to-Emitter Voltage ( $V_{CE}$ ) . . . . .	-9	volts
DC Emitter Current ( $I_E$ ) . . . . .	1	ma
Resistance $r_{bb}$ . . . . .	40	ohms
Conductance $g_{b'e}$ . . . . .	640	$\mu$ hos
Conductance $g_{ce}$ (Approx.) . . . . .	0	$\mu$ hos
Conductance $g_{b'c}$ (Approx.) . . . . .	0	$\mu$ hos
Capacitance $C_{b'e}$ . . . . .	200	$\mu$ f
Capacitance $C_{b'c}$ . . . . .	1.7	$\mu$ f
Interlead Capacitance between collector and base leads with interlead shield connected to ground and all leads cut to 5/16" . . . . .	0.094	$\mu$ f
Intrinsic Transconductance ( $g_m$ ) . . . . .	37000	$\mu$ hos
Frequency <sup>•</sup> for unity power amplification . . . . .	132	Mc

## Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage . . . . .	-9	volts
DC Emitter Current . . . . .	1	ma
Forward Current Transfer Ratio <sup>•</sup> . . . . .	0.984	
Frequency at which the forward current transfer ratio drops to 0.707 times its value at 1 kc . . . . .	30	Mc

## Typical Operation, At Ambient Temperature of 25° C:

## Common-Emitter Circuit, Base Input

At frequency of	1.5	10.7	Mc
DC Collector-to-Emitter Voltage . . . . .	-9	-9	volts
DC Emitter Current . . . . .	1	1	ma
DC Base-to-Emitter Voltage . . . . .	-0.2	-0.2	volt
Input Resistance, AC output circuit shorted . . . . .	1350	170	ohms
Output Resistance, AC input circuit shorted . . . . .	70000	4500	ohms
Power Gain <sup>▲</sup> . . . . .	45	24	db

■ Measured at 1 kc.

\* As derived from corresponding equivalent circuit shown under type 2N104.

• This frequency (figure of merit) may be calculated from the equation

$$f = \frac{1}{4\pi} \sqrt{\frac{g_m}{r_{bb} \cdot C_{b'c} \cdot C_{b'e}}}$$

▲ Measured in a single-tuned unilateralized circuit matched to the generator and load impedances for maximum transfer of power. Transformer insertion losses not included.

## OPERATING CONSIDERATIONS

The 2N274 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.





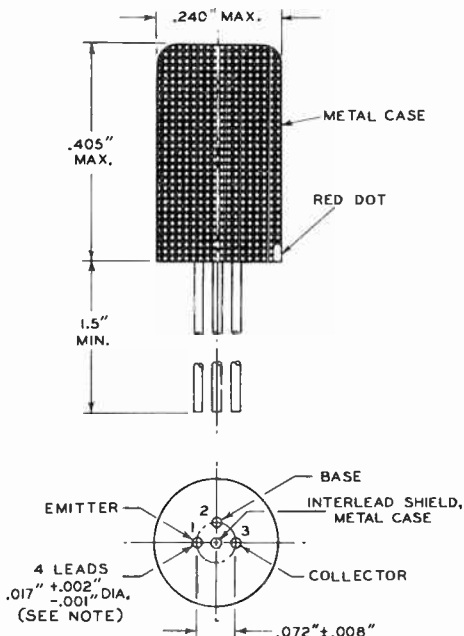
2N274

2N274

### DRIFT TRANSISTOR

The flexible leads of the 2N274 are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using the 2N274, the temperature of the solder should not exceed 230° C for a maximum immersion period of 10 seconds.



92CS-9266R1

NOTE: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.050" AND 0.250" FROM THE PLANE OF THE ACTUAL BOTTOM OF THE BASE. BETWEEN 0.250" AND 1.50", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

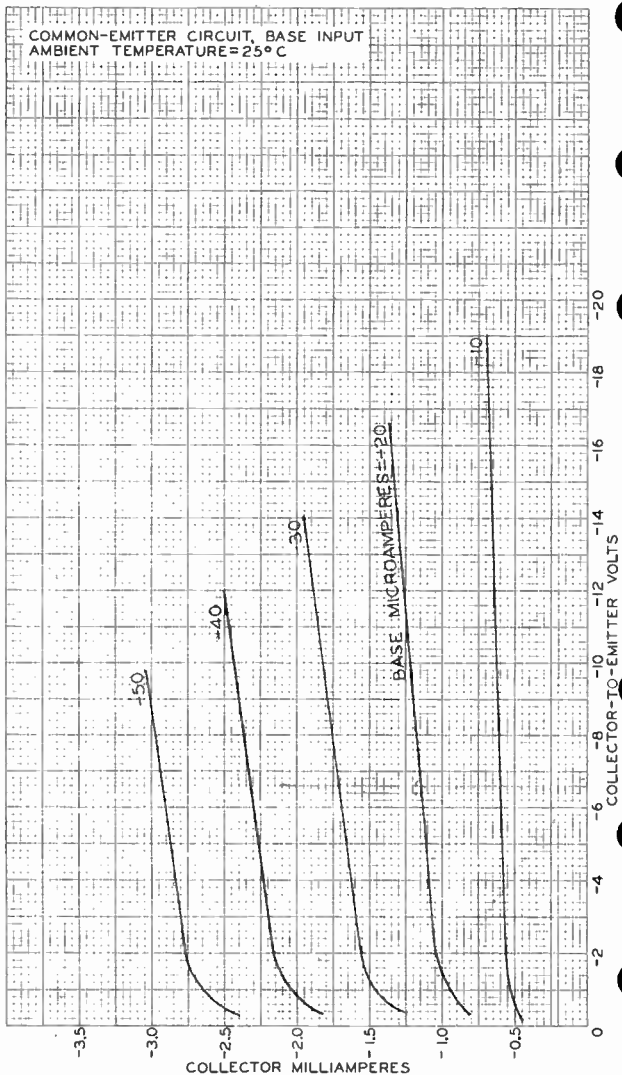
2N274



2N274

# AVERAGE COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE = 25°C



COLLECTOR MILLIAMPERES

SEMICONDUCTOR DIVISION

RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

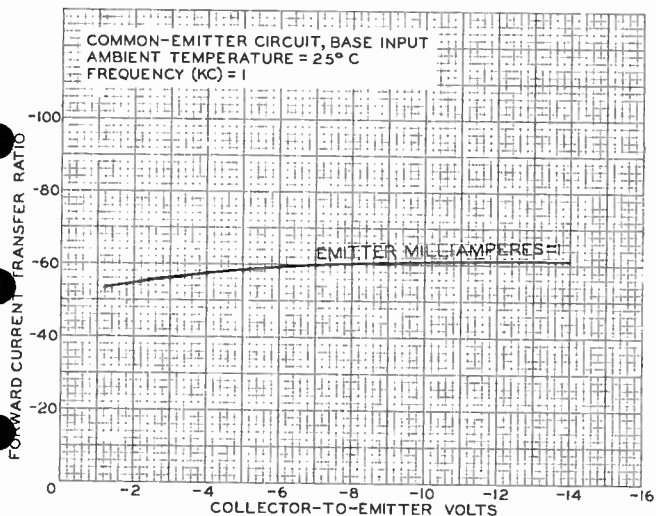
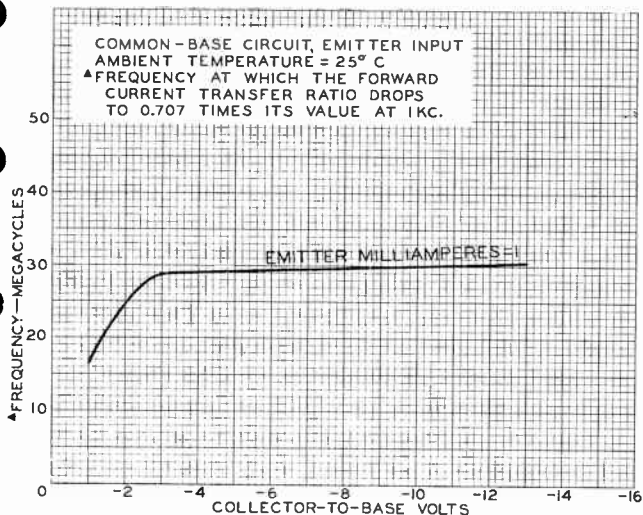
92CM-9107



2N274

2N274

### AVERAGE CHARACTERISTICS

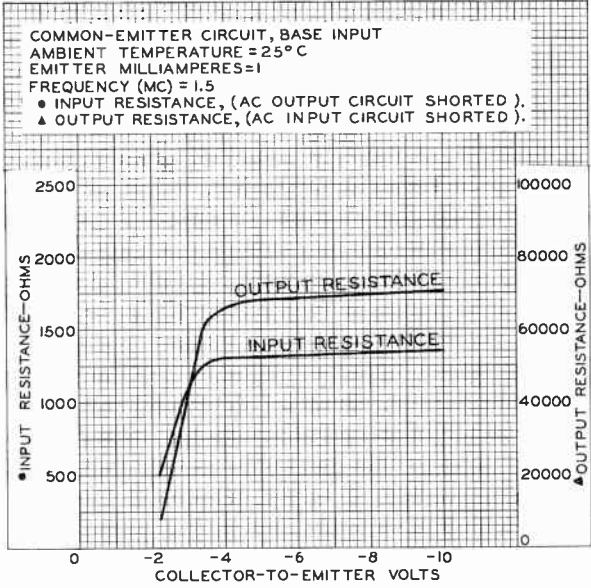
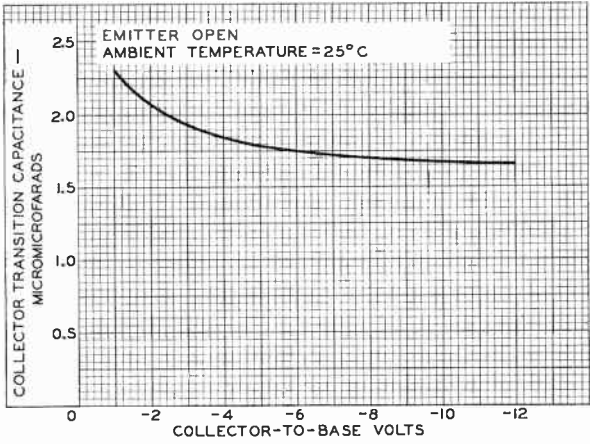


2N274



2N274

### AVERAGE CHARACTERISTICS



## Power Transistor

## GERMANIUM P-N-P ALLOY TYPE

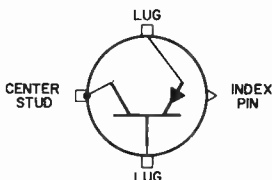
For Power Switching and Amplifier Service  
in Industrial and Military Applications

## GENERAL DATA

## Mechanical:

Operating Position. . . . .	Any
Maximum Seated Length . . . . .	0.520"
Maximum Diameter. . . . .	1.250"
Dimensional Outline . . . . .	JEDEC No. TO-36
Case. . . . .	Welded, Metal
Seals . . . . .	Hermetic
Terminal Diagram (See <i>Dimensional Outline</i> ):	

BOTTOM VIEW



## INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and audio-amplifier, relay- and solenoid-actuating circuits

## Maximum and Minimum Ratings, Absolute-Maximum Values:

## COLLECTOR-TO-BASE VOLTAGE:

With emitter-to-base reverse biased

(Dc emitter-to-base volts = 1.5). . . . .	-40 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-20 max.	volts
COLLECTOR CURRENT . . . . .	-15 max.	amp
EMITTER CURRENT . . . . .	15 max.	amp
BASE CURRENT. . . . .	-4 max.	amp

TRANSISTOR DISSIPATION:<sup>a</sup>

At case temperatures<sup>b</sup> of 25° C or below . . . . . 150 max. watts ←

CASE-TEMPERATURE<sup>b</sup> RANGE:

Operating and storage . . . . . -65 to +100 °C ←

## Typical Operation:

In a common-emitter, base-input, power-switching circuit at case temperature<sup>b</sup> of 25° C

DC Supply Voltage . . . . .	-12	volts
DC Base-Bias Voltage. . . . .	6	volts
"On" DC Collector Current . . . . .	-12	amp
"Turn-On" Base Current. . . . .	-2	amp
"Turn-Off" Base Current . . . . .	0	amp

← Indicates a change.



# 2N277

## Switching Time:

Rise time . . . . .	15	$\mu$ sec
Fall time . . . . .	15	$\mu$ sec

<sup>a</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

<sup>b</sup> Measured at any point on seating surface.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and at case temperature<sup>b</sup> of 25° C unless otherwise specified  
Min. Typical Max.

### DC Collector-to-Emitter

#### Breakdown Voltage:

With base connected to emitter, dc collector

amperes = -0.3 . . . . .  $BV_{CES}$  -40 - - volts

With base open:

For dc collector amperes = -0.3 . . . . .  $BV_{CEO}$  - - -40 - volts

For dc collector amperes = -1<sup>c</sup> . . . . . -25 - - volts

### DC Base-to-Emitter Voltage

for dc collector-to-emitter volts = -2, dc collector amperes = -5.

$V_{BE}$  - - -0.65 - volt

### DC Collector-to-Emitter

Saturation Voltage for dc collector amperes =

-12, dc base amperes = -2 . . . . .  $V_{CE(sat)}$  - - -0.3 - volt

### DC Emitter Voltage for dc

collector volts = -40, dc emitter current = 0.

$V_{EB}$  - - - -1 - volt

### DC Punch-Through Voltage.

for dc emitter volts = -20, dc collector

current = 0 . . . . .  $V_{PT}$  -40 - - - ma

### DC Collector-Cutoff Current:

With dc collector volts = -2, dc emitter

current = 0 . . . . .  $I_{CBO}$  - - -100 -  $\mu$ a

With dc collector volts = -40, dc emitter

current = 0 . . . . . - - -2 -4 ma

With dc collector volts = -40, dc emitter

current = 0, case temperature<sup>b</sup> = 71° C. . . . . - - -15 ma

### DC Current Transfer Ratio

for dc collector-to-emitter volts = -2, dc collector amperes =

-5 . . . . .  $h_{FE}$  35 - 70

-12 . . . . . - 25 -

→ Indicates a change.



Beta-Cutoff Frequency for dc collector-to-emitter volts = -6, dc collector amperes = -5. . . . .	$f_{ae}$	-	10	-	kc
Thermal Resistance: Junction-to-case. . . . .	$R_T$	-	0.35	0.5	$^{\circ}\text{C}/\text{watt}$
Thermal Capacity for pulse duration of 1 to 10 milliseconds. . . . .		-	0.075	-	watt- sec/ $^{\circ}\text{C}$
Thermal Time Constant . . . .	$\tau_1$	-	26.25	-	msec

<sup>b</sup> Measured at any point on seating surface.

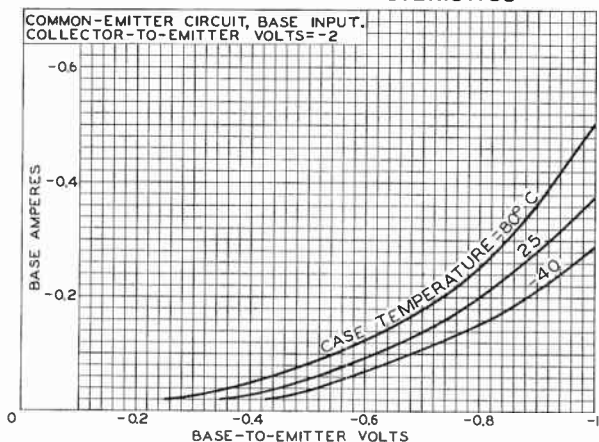
<sup>c</sup> Tested by sweep method to prevent excessive heating of collector junction.

PERFORMANCE TESTS,  
OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
and  
RATING CHART

shown under Type 2N173 also apply to the 2N277

← Indicates a change.

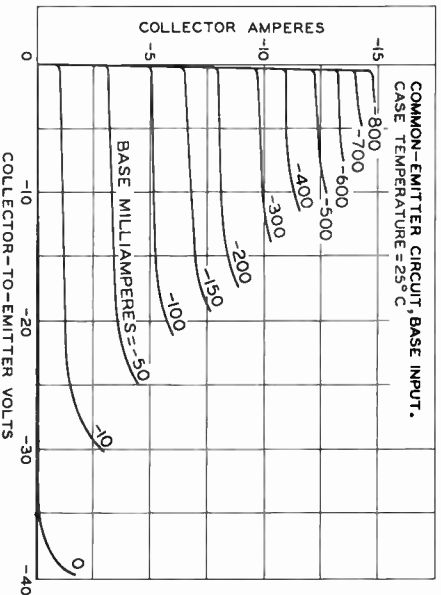
## TYPICAL BASE CHARACTERISTICS



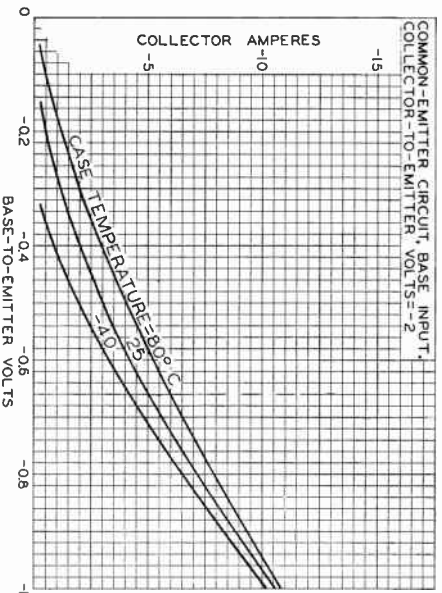
92CS-10703



## TYPICAL COLLECTOR CHARACTERISTICS



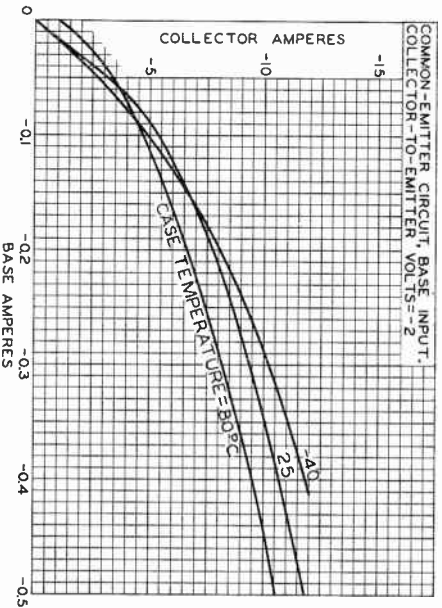
## TYPICAL CHARACTERISTICS





# 2N277

## TYPICAL CHARACTERISTICS



92CS-10712

World Radio History



RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division  
Somerville, N. J.

DATA 3  
8-61



## Power Transistor

## GERMANIUM P-N-P ALLOY TYPE

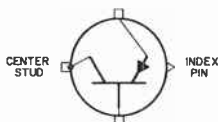
For Power Switching and Amplifier Service  
in Industrial and Military Applications

## GENERAL DATA

## Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	1.230"
Maximum Seated Length. . . . .	0.520"
Maximum Diameter. . . . .	1.250"
Dimensional Outline. . . . .	JEDEC No. TO-36
Case. . . . .	Welded, Metal
Seals. . . . .	Hermetic
Terminal Diagram (See <i>Dimensional Outline</i> ):	

## BOTTOM VIEW



## INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and audio-amplifier, relay- and solenoid-actuating circuits

## Maximum and Minimum Ratings, Absolute-Maximum Values:

## COLLECTOR-TO-BASE VOLTAGE:

With emitter-to-base reverse biased

(DC emitter-to-base volts = 1.5). . . . . -40 max. volts

EMITTER-TO-BASE VOLTAGE . . . . . -20 max. volts

COLLECTOR CURRENT . . . . . -15 max. amp

EMITTER CURRENT . . . . . 15 max. amp

BASE CURRENT. . . . . -4 max. amp

TRANSISTOR DISSIPATION:<sup>▲</sup>

At case temperature of 25° C. . . . . 70 max. watts

## CASE-TEMPERATURE RANGE:

Continuous operation. . . . . -65 to +95 °C

Intermittent operation. . . . . -65 to +100 °C

Storage . . . . . -65 to +100 °C

## Typical Operation:

In a common-emitter, base-input, power-switching circuit at case temperature of 25° C

DC Supply Voltage . . . . . -12 volts

DC Base-Bias Voltage. . . . . 6 volts

"On" DC Collector Current . . . . . -12 amp

"Turn-On" Base Current. . . . . -2 amp

"Turn-Off" Base Current . . . . . 0 amp



# 2N277

## Switching Time:

Rise time . . . . .	15	$\mu\text{sec}$
Fall time . . . . .	15	$\mu\text{sec}$

▲ See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and case temperature of 25° C unless otherwise specified

Min. Typical Max.

DC Collector-to-Emitter Breakdown Voltage:						
With base connected to emitter, dc collector amperes = -0.3 . . . . .						
$BV_{CES}$	-40	-	-			volts
With base open:						
For dc collector amperes = -0.3 . . . . .						
$BV_{CEO}$	-	-40	-			volts
For dc collector amperes = -1 <sup>•</sup> . . . . .						
	-25	-	-			volts
DC Base-to-Emitter Voltage* for dc collector-to-emitter volts = -2, dc collector amperes = -5 . . . . .						
$V_{BE}$	-	-0.65	-			volt
DC Collector-to-Emitter Saturation Voltage* for dc collector amperes = -12, base amperes = -2 . . . . .						
$V_{CE}$	-	-0.3	-			volt
DC Emitter Voltage for dc collector volts = -40, emitter amperes = 0 . . . . .						
$V_{EB}$	-	-	-1			volt
DC Punch-Through Voltage. $V_P$						
	-40	-	-			volts
DC Emitter-Cutoff Current for dc emitter volts = -20, dc collector amperes = 0 . . . . .						
$I_{EBO}$	-	-1	-8			ma
DC Collector-Cutoff Current: $I_{CBO}$						
With dc collector volts = -2, dc emitter amperes = 0 . . . . .						
	-	-100	-			$\mu\text{a}$
With dc collector volts = -40, dc emitter amperes = 0 . . . . .						
	-	-2	-8			ma
With dc collector volts = -40, dc emitter amperes = 0, case temperature = 71° C . . . . .						
	-	-	-15			ma
DC Current Transfer Ratio* $h_{FE}$						
for dc collector-to-emitter volts = -2, dc collector amperes =						
	-5 . . . . .	35	-	70		
	-12 . . . . .	-	25	-		



Beta-Cutoff Frequency* for dc collector-to-emitter volts = -6, dc collector amperes = -5. . . . .	$f_{ae}$	-	10	-	kc
Thermal Resistance: Junction-to-case. . . . .	$R_T$	-	0.7	1	$^{\circ}\text{C}/\text{watt}$
Thermal Capacity for pulse duration of 1 to 10 milliseconds. . . . .		-	0.075	-	$\text{watt-sec}/^{\circ}\text{C}$
Thermal Time Constant . . .	$\tau_1$	-	52.5	-	msec

\* Sweep voltage used to perform test.

★ Measured in a common-emitter, base-input circuit.

### OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

Electrical connection can be made to the base and emitter terminals by means of clips or by soldering directly to the terminals. When soldering connections are made to the terminals, care should be taken to conduct excessive heat away from the terminal seals, otherwise the heat of the soldering operation will crack the glass seals of the terminals and damage the transistor.

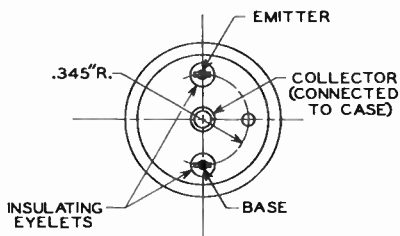
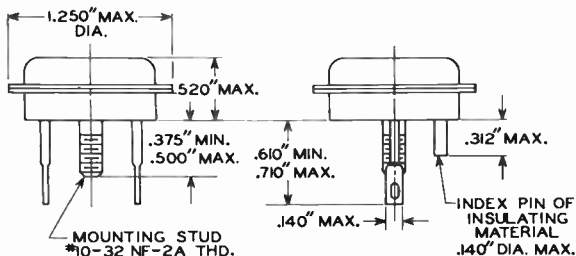
This transistor is provided with a single-ended stud for mounting to a heat sink and for electrical connection to the collector. (See accompanying *Suggested Mounting Arrangement*). Electrical connection to the base and to the emitter is made to their respective terminals.

It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.

The maximum torque on mounting stud should not exceed 12 inch-pounds.

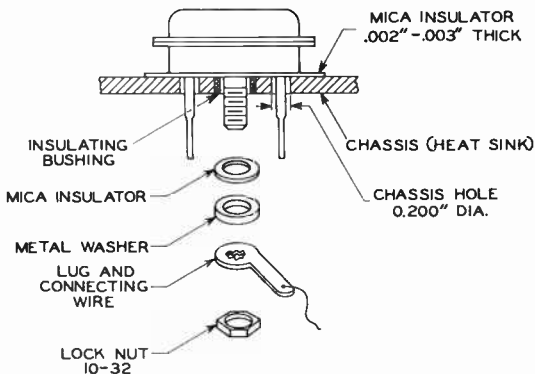


# 2N277



92CM-10612R1

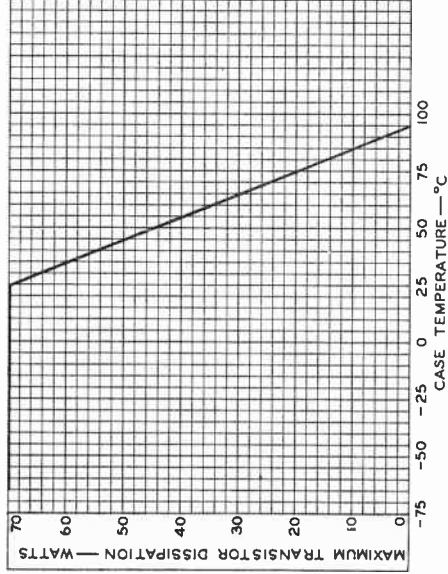
## SUGGESTED MOUNTING ARRANGEMENT



92CS-10624R1

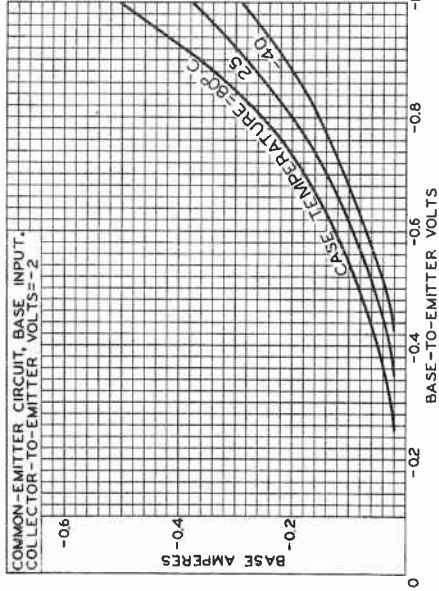


## RATING CHART



92CS-10701

## TYPICAL BASE CHARACTERISTICS

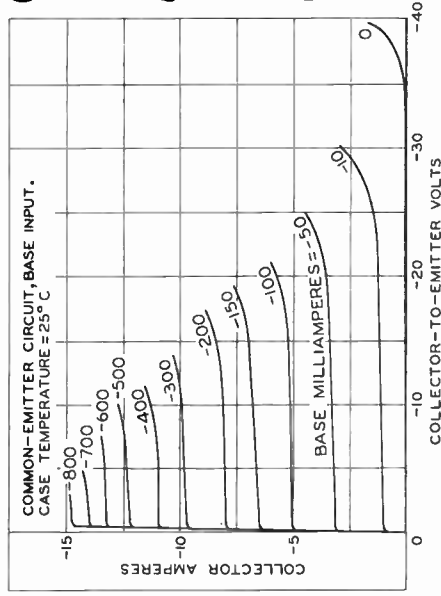


92CS-10703



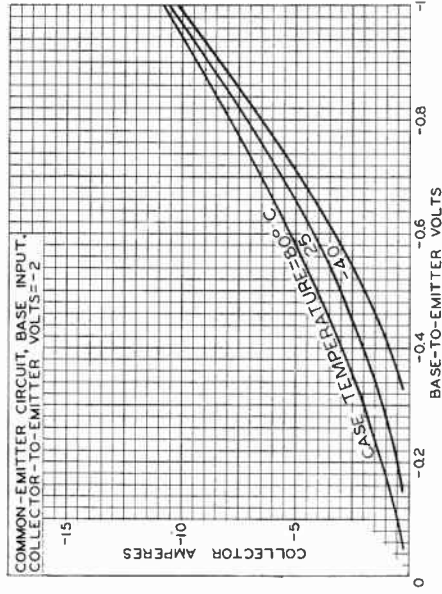
# 2N277

## TYPICAL COLLECTOR CHARACTERISTICS



92CS-10725

## TYPICAL CHARACTERISTICS

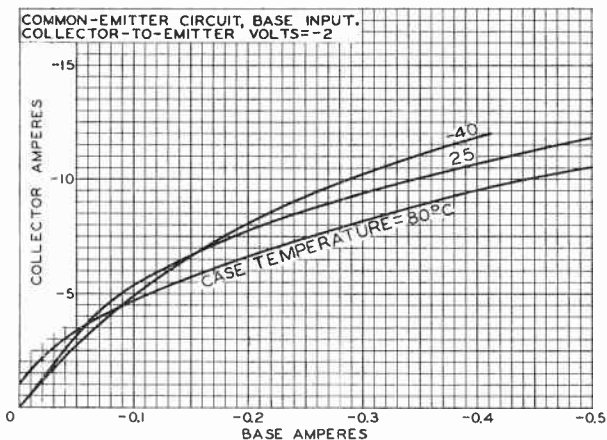


92CS-10709





## TYPICAL CHARACTERISTICS



92CS-10712





## Power Transistor

## GERMANIUM P-N-P ALLOY TYPE

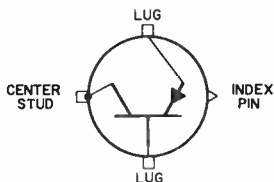
For Power Switching and Amplifier Service  
in Industrial and Military Applications

## GENERAL DATA

## Mechanical:

Operating Position. . . . .	Any
Maximum Seated Length . . . . .	0.520"
Maximum Diameter. . . . .	1.250"
Dimensional Outline . . . . .	JEDEC No. TO-36
Case. . . . .	Welded, Metal
Seals . . . . .	Hermetic
Terminal Diagram (See <i>Dimensional Outline</i> ):	

## BOTTOM VIEW



## INDUSTRIAL SERVICE

*Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and audio-amplifier, relay- and solenoid-actuating circuits*

## Maximum and Minimum Ratings, Absolute-Maximum Values:

## COLLECTOR-TO-BASE VOLTAGE:

With emitter-to-base reverse biased

(DC emitter-to-base volts = 1.5). . . . . -50 max. volts

EMITTER-TO-BASE VOLTAGE . . . . . -30 max. volts

COLLECTOR CURRENT . . . . . -15 max. amp

EMITTER CURRENT . . . . . 15 max. amp

BASE CURRENT. . . . . -4 max. amp

TRANSISTOR DISSIPATION:<sup>a</sup>

At case temperatures<sup>b</sup> of 25° C or below . . . . . 150 max. watts

CASE-TEMPERATURE<sup>b</sup> RANGE:

Operating and storage . . . . . -65 to +100 °C

## Typical Operation:

*In a common-emitter, base-input, power-switching circuit at case temperature<sup>b</sup> of 25° C*

DC Supply Voltage . . . . . -12 volts

DC Base-Bias Voltage. . . . . 6 volts

"On" DC Collector Current . . . . . -12 amp

"Turn-On" Base Current. . . . . -2 amp

"Turn-Off" Base Current . . . . . 0 amp

← Indicates a change.



# 2N278

## Switching Time:

Rise time . . . . .	15	$\mu$ sec
Fall time . . . . .	15	$\mu$ sec

<sup>a</sup> See accompanying *Rating Chart* and also *Transistor-Dissipation Rating Chart* in *General Section*.

<sup>b</sup> Measured at any point on seating surface.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and at case temperature<sup>b</sup> of 25° C unless otherwise specified

Min. Typical Max.

DC Collector-to-Emitter Breakdown Voltage:					
With base connected to emitter, dc collector amperes = -0.3 . . . . .					
	$BV_{CES}$	-45	-	-	volts
With base open:					
For dc collector amperes = -0.3 . . . . .					
	$BV_{CEO}$	-	-45	-	volts
For dc collector amperes = -1 <sup>c</sup> . . . . .					
		-30	-	-	volts
DC Base-to-Emitter Voltage for dc collector-to-emitter volts = -2, dc collector amperes = -5 . . . . .					
	$V_{BE}$	-	-0.65	-	volt
DC Collector-to-Emitter Saturation Voltage for dc collector amperes = -12, dc base amperes = -2 . . . . .					
	$V_{CE}$	-	-0.3	-0.7	volt
DC Emitter Voltage for dc collector volts = -50, dc emitter current = 0 . . . . .					
	$V_{EB}$	-	-	-1	volt
DC Punch-Through Voltage . . . . .					
	$V_{PT}$	-50	-	-	volts
DC Emitter-Cutoff Current for dc emitter volts = -30, dc collector current = 0 . . . . .					
	$I_{EBO}$	-	-1	-4	ma
DC Collector-Cutoff Current:					
With dc collector volts = -2, dc emitter current = 0 . . . . .					
	$I_{CBO}$	-	-100	-	$\mu$ a
With dc collector volts = -50, dc emitter current = 0 . . . . .					
		-	-2	-4	ma
With dc collector volts = -50, dc emitter current = 0, case temperature <sup>b</sup> = 71° C . . . . .					
		-	-	-15	ma

→ indicates a change.



DC Current Transfer Ratio	$h_{FE}$			
for dc collector-to-emitter volts = -2, dc collector amperes =				
-5 . . . . .	35	-	70	
-12 . . . . .	-	25	-	
Beta-Cutoff Frequency				
for dc collector-to-emitter volts = -6, dc collector amperes = -5 . . . . .	$f_{ae}$	-	10	kc
Thermal Resistance:				
Junction-to-case . . . . .	$R_T$	-	0.35	0.5 °C/watt
Thermal Capacity for pulse duration of 1 to 10 milliseconds . . . . .		-	0.075	watt-sec/°C
Thermal Time Constant . . . . .	$\tau_1$	-	52.5	msec

<sup>b</sup> Measured at any point on seating surface.

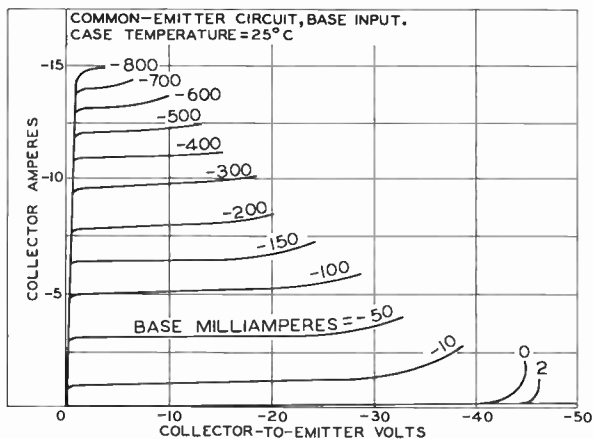
<sup>c</sup> Tested by sweep method to prevent excessive heating of collector junction.

**PERFORMANCE TESTS,**  
**OPERATING CONSIDERATIONS,**  
**DIMENSIONAL OUTLINE,**  
**SUGGESTED MOUNTING ARRANGEMENT,**  
**RATING CHART,**  
**TYPICAL BASE-CHARACTERISTICS CURVES,**  
**and**  
**TYPICAL CHARACTERISTICS CURVES**  
 shown under Type 2N173 also apply to the 2N278

← Indicates a change.



## TYPICAL COLLECTOR CHARACTERISTICS



92CS-10738

## Power Transistor

## GERMANIUM P-N-P ALLOY TYPE

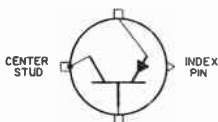
For Power Switching and Amplifier Service  
in Industrial and Military Applications

## GENERAL DATA

## Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	1.230"
Maximum Seated Length. . . . .	0.520"
Maximum Diameter. . . . .	1.250"
Dimensional Outline. . . . .	JEDEC No. TO-36
Case. . . . .	Welded, Metal
Seals. . . . .	Hermetic
Terminal Diagram (See <i>Dimensional Outline</i> ):	

## BOTTOM VIEW



## INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter, chopper,  
voltage- and current-regulator, dc- and audio-  
amplifier, relay- and solenoid-actuating circuits

## Maximum and Minimum Ratings, Absolute-Maximum Values:

## COLLECTOR-TO-BASE VOLTAGE:

With emitter-to-base reverse biased (DC emitter-to-base volts = 1.5). . . . .	-50 max.	volts
EMITTER-TO-BASE VOLTAGE. . . . .	-30 max.	volts
COLLECTOR CURRENT. . . . .	-15 max.	amp
EMITTER CURRENT. . . . .	15 max.	amp
BASE CURRENT. . . . .	-4 max.	amp
TRANSISTOR DISSIPATION: <sup>A</sup> At case temperature of 25° C. . . . .	70 max.	watts
CASE-TEMPERATURE RANGE:		
Continuous operation. . . . .	-65 to +95	°C
Intermittent operation. . . . .	-65 to +100	°C
Storage. . . . .	-65 to +100	°C

## Typical Operation:

In a common-emitter, base-input, power-switching  
circuit at case temperature of 25° C

DC Supply Voltage. . . . .	-12	volts
DC Base-Bias Voltage. . . . .	6	volts
"On" DC Collector Current. . . . .	-12	amp
"Turn-On" Base Current. . . . .	-2	amp
"Turn-Off" Base Current. . . . .	0	amp



# 2N278

## Switching Time:

Rise time . . . . .	15	$\mu$ Sec
Fall time . . . . .	15	$\mu$ Sec

▲ See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and case temperature of 25° C unless otherwise specified  
Min. Typical Max.

### DC Collector-to-Emitter

#### Breakdown Voltage:

With base connected to emitter, dc collector

amperes = -0.3. . . . .  $V_{CES}$  -45 - - volts

With base open:  $V_{CEO}$

For dc collector

amperes = -0.3. . . - -45 - volts

For dc collector

amperes = -1\* . . . -30 - - volts

### DC Base-to-Emitter

Voltage\* for dc collector-to-emitter volts = -2, dc collector

amperes = -5. . . . .  $V_{BE}$  - -0.65 - volts

### DC Collector-to-Emitter

#### Saturation Voltage\*

for dc collector

amperes = -12, base

amperes = -2. . . . .  $V_{CE}$  - -0.3 -1 volt

### DC Emitter Voltage for

dc collector volts =

-50, emitter amperes

= 0 . . . . .  $V_{EB}$  - - -1 volt

### DC Punch-Through Voltage.

$V_P$  -50 - - volts

### DC Emitter-Cutoff Current

for dc emitter volts =

-30, dc collector

amperes = 0 . . . . .  $I_{EBO}$  - -1 -8 ma

### DC Collector-Cutoff

Current:

$I_{CBO}$

With dc collector volts

= -2, dc emitter

amperes = 0 . . . . . - -100 -  $\mu$ a

With dc collector volts

= -50, dc emitter

amperes = 0 . . . . . - -2 -8 ma

With dc collector volts

= -50, dc emitter

amperes = 0, case

temperature = 71° C . - - -15 ma





DC Current Transfer Ratio\*  $h_{FE}$

for dc collector-to-emitter volts = -2, dc collector amperes =

-5 . . . . .	35	-	70
-12 . . . . .	-	25	-

Beta-Cutoff Frequency\*

for dc collector-to-emitter volts = -6, dc collector amperes = -5 .  $f_{ae}$

-	10	-	kc
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Thermal Resistance:

Junction-to-case . . . .  $R_T$  - 0.7 1 °C/watt

Thermal Capacity for pulse

duration of 1 to 10

milliseconds . . . . . - 0.075 - watt-sec/°C

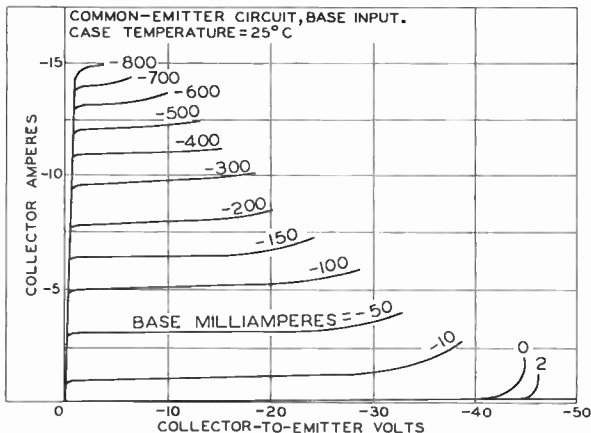
Thermal Time Constant. . .  $\tau_1$  - 52.5 - msec

• Sweep voltage used to perform test.

\* Measured in a common-emitter, base-input circuit.

OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHART,  
TYPICAL BASE-CHARACTERISTICS CURVES,  
and TYPICAL CHARACTERISTICS CURVES,  
shown under Type 2N277 also apply to the 2N278

## TYPICAL COLLECTOR CHARACTERISTICS



92CS-10738







2N301

# POWER TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For audio-frequency power applications

2N301

## GENERAL DATA

Electrical, For Mounting-Flange Temperature of 25 °C:

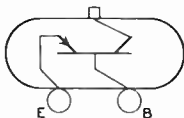
Minimum DC Collector-to-Base Voltage for dc collector current of -1 milli- ampere with emitter open. . . . .	-40	volts
Minimum DC Emitter-to-Base Voltage for dc emitter current of -1 milli- ampere with collector open. . . . .	-12	volts
Maximum DC Collector Current for dc collector-to-base voltage of -12 volts with emitter open. . . . .	-220	µa
Maximum DC Collector Current for dc collector-to-base voltage of -0.5 volt with emitter open. . . . .	-50	µa

### Mechanical:

Mounting Position . . . . .	Any
Maximum Overall Length. . . . .	0.875"
Maximum Seated Length . . . . .	0.475"
Maximum Length of Mounting Flange . . . . .	1.562"
Maximum Width of Mounting Flange. . . . .	1.031"
Case. . . . .	Plated Steel, Insulated
Mounting Flange . . . . .	Copper
Envelope Seals. . . . .	Hermetic
Terminal Connections (See Dimensional Outline):	

E - Emitter

B - Base



MOUNTING FLANGE -  
Collector

## AUDIO-FREQUENCY POWER AMPLIFIER -- Class A

### Maximum Ratings, Absolute Values:

PEAK COLLECTOR-TO-BASE VOLTAGE. . . . .	-40 max.	volts
DC COLLECTOR-TO-BASE VOLTAGE (For inductive load) . . . . .	-20 max.	volts
DC EMITTER-TO-BASE VOLTAGE. . . . .	-12 max.	volts
PEAK COLLECTOR CURRENT. . . . .	-2 max.	amp
DC COLLECTOR CURRENT. . . . .	-1 max.	amp
PEAK EMITTER CURRENT. . . . .	2 max.	amp
DC EMITTER CURRENT. . . . .	1 max.	amp

### TRANSISTOR DISSIPATION:

For continuous operation:\*

For mounting-flange temperatures up to 55 °C . . . . .	12 max.	watts
For mounting-flange temperature of 71 °C. . . . .	5.5 max.	watts

\* The maximum transistor-dissipation rating is reduced 0.4 watt for each degree centigrade the mounting-flange temperature is increased above 55 °C.

2N301



2N301

## POWER TRANSISTOR

For intermittent operation:\*

For mounting-flange temperature of 80 °C. . . . .	7.5 max.	watts
MOUNTING-FLANGE TEMPERATURE (During operation). . . . .	85 max.	°C
STORAGE-TEMPERATURE RANGE . . . . .	-65 to +85	°C

Characteristics, For Mounting-Flange Temperature of 25 °C:

Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage . . . . .	-1.5	-1.5	volts
DC Collector Current. . . . .	-0.5	-1	amp
Signal Frequency. . . . .	1	-	kc
Input Resistance. . . . .	23	37	ohms
Current Transfer Ratio. . . . .	-75	-	
Large-Signal DC Current Transfer Ratio . . . . .	-	70	

Typical Operation<sup>†</sup>, At Ambient Temperature of 55 °C:

Common-Emitter Circuit, Base Input

DC Supply Voltage . . . . .	14.4	volts
DC Collector-to-Emitter Voltage . . . . .	-13.6	volts
Emitter Resistor (Unbypassed) . . . . .	1	ohm
DC Base-to-Emitter Voltage. . . . .	-0.24	volt
DC Collector Current:		
Peak. . . . .	-0.8	amp
Zero-signal . . . . .	-0.4	amp
Signal-Source Impedance . . . . .	50	ohms
Load impedance. . . . .	34	ohms
Signal Frequency. . . . .	400	cps
Circuit Efficiency♦ . . . . .	47	%
Power Gain♦ . . . . .	32.5	db
Total Harmonic Distortion . . . . .	10 max.	%
Max.-Signal Power Output♦ . . . . .	2.7	watts

## AUDIO-FREQUENCY POWER AMPLIFIER -- Class B

Maximum Ratings, Absolute Values:

PEAK COLLECTOR-TO-BASE VOLTAGE. . . . .	-40 max.	volts
DC COLLECTOR-TO-BASE VOLTAGE (For inductive load) . . . . .	-20 max.	volts
DC EMITTER-TO-BASE VOLTAGE. . . . .	-12 max.	volts
PEAK COLLECTOR CURRENT. . . . .	-2 max.	amp
DC COLLECTOR CURRENT. . . . .	-1 max.	amp
PEAK EMITTER CURRENT. . . . .	2 max.	amp
DC EMITTER CURRENT. . . . .	1 max.	amp

\* An aluminum chassis 7" x 11" x 1/16" mounted horizontally in free air is used as a heat sink.

♦, ◆: See next page.



2N301

2N301

## POWER TRANSISTOR

## TRANSISTOR DISSIPATION:

For continuous operation:\*

For mounting-flange temperatures up to 55 °C . . . . .	12 max.	watts
For mounting-flange temperature of 71 °C. . . . .	5.5 max.	watts

For intermittent operation:\*

For mounting-flange temperature of 80 °C. . . . .	7.5 max.	watts
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MOUNTING-FLANGE TEMPERATURE (During operation). . . . .	85 max.	°C
STORAGE-TEMPERATURE RANGE . . . . .	-65 to +85	°C

## Characteristics, For Mounting-Flange Temperature of 25 °C:

## Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage . . . . .	-1.5	-1.5	volts
DC Collector Current. . . . .	-0.5	-1	amp
Signal Frequency. . . . .	1	-	kc
Input Resistance. . . . .	23	37	ohms
Current Transfer Ratio. . . . .	-75	-	
Large-Signal DC Current Transfer Ratio . . . . .	-	70	

Typical Push-Pull Operation<sup>†</sup>, At Ambient Temperature of 55 °C:

## Common-Emitter Circuit, Base Input

Unless otherwise specified, values are for 2 transistors

DC Supply Voltage . . . . .	14.4	volts
DC Base-to-Emitter Voltage (Zero signal) . . . . .	-0.13	volt
Peak Collector Current (Per transistor) . . . . .	-2	amp
Zero-Signal DC Collector Current (Per transistor) . . . . .	-0.05	amp
Max.-Signal DC Collector Current (Per transistor) . . . . .	-0.64	amp
Signal-Source Impedance (Base to base) . . . . .	60	ohms
Load Impedance (Collector to collector). . . . .	24	ohms
Signal Frequency. . . . .	400	cps
Circuit Efficiency♦ . . . . .	67	%
Power Gain♦ . . . . .	30	db
Total Harmonic Distortion . . . . .	10 max.	%
Max.-Signal Power Output♦ . . . . .	12	watts

\* The term "intermittent" is used to identify operating conditions in which no operating or "on" period exceeds 100 milliseconds. Each period is followed by an "off" period of at least the same or greater duration.

† The maximum transistor-dissipation rating is for a junction temperature 75 degrees centigrade the mounting-flange temperature is 55 degrees centigrade.

♦, †: See next page.



2N301

## POWER TRANSISTOR

- ◆ Measured at the primary of the output transformer.
- An aluminum chassis 7" x 11" x 1/16" mounted horizontally in free air is used as a heat sink. A 1/8" anodized-aluminum insulator is mounted between the mounting flange of each transistor and the chassis.

## OPERATING CONSIDERATIONS

The base and emitter pins of the 2N301 fit the Loranger Mfg. Corp. Socket No. 2149, or equivalent. When a socket is not used, connections can be soldered directly to the base and emitter pins. Soldering of the connections to the pins may be made close to the pin seals provided care is taken to conduct excessive heat away from the pin seals. Otherwise, the heat of the soldering operation will crack the glass seals of the pins and damage the transistor.

Depending upon application, electrical connection to the collector is made either directly to the chassis or to the mounting lug (*See Suggested Mounting Arrangement*). Under no circumstances should a connection be soldered to the mounting flange because the heat of the soldering operation will permanently damage the transistor.

In most applications, the metal chassis may be used as a heat sink. Depending upon the application, the chassis (heat sink) may be connected either to the positive or negative terminal of the voltage supply. In applications where the chassis is connected to the positive terminal of the voltage supply, it will be necessary to use a 1/8" anodized-aluminum insulator having high thermal conductivity or a 0.002" mica insulator between the mounting flange and the chassis. An aluminum washer should be drilled or punched to provide the two mounting holes and the clearance holes for the emitter and base pins. The burrs should then be removed from the washer and the washer finally anodized. To insure the anodized insulating layer is not destroyed during mounting, it will also be necessary to remove the burrs from the holes in the chassis. Furthermore, to prevent a short circuit between the mounting bolt and the chassis, it is important that a fiber washer be used between the bolt and the chassis. (*See Suggested Mounting Arrangement*).

The 2N301 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

In class A service when the chassis is connected to the negative terminal of the voltage supply, the mounting flange may be directly fastened to the chassis. In this class of service, degeneration in the biasing circuit may cause reduced power gain. To minimize degeneration, it is necessary to provide positive feedback in the input circuit. To insure stable operation and low distortion, it



2N301

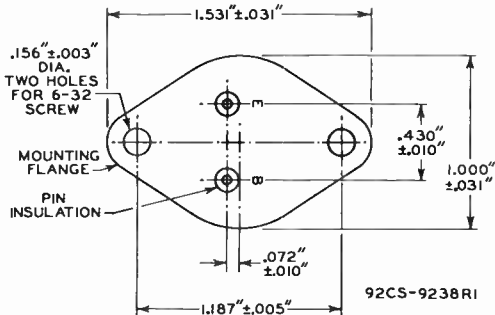
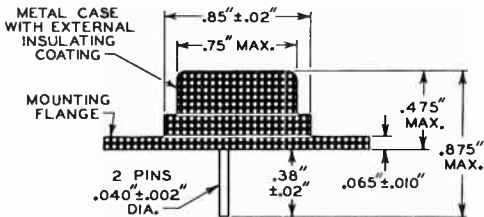
2N301

# POWER TRANSISTOR

is necessary to provide some degeneration in the emitter circuit. This degeneration may be provided by the use of an unbypassed 1-ohm resistor in the emitter circuit.

In *class B service*, when the 2N301 is operated at mounting-flange temperatures other than 25 °C, the base-to-emitter voltage should be reduced or increased by approximately 0.002 volt for each degree the mounting-flange temperature is above or below 25 °C, respectively. When this transistor is operated under varying mounting-flange temperatures, some form of temperature compensation may be used in the base-to-emitter circuit to hold the operating point constant.

In *class B push-pull service*, it is necessary to insulate the mounting flange (collector terminal) of each transistor from the chassis and from the mounting flange of the other in order to prevent short circuiting the collector load. The *Suggested Mounting Arrangement* will insure good electrical contact and maximum transfer of heat.



E=EMITTER  
 B=BASE  
 MOUNTING FLANGE=COLLECTOR

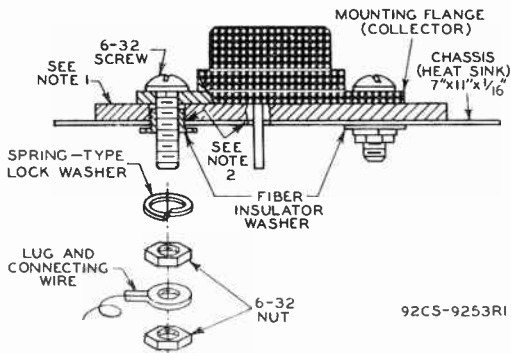
2N301



2N301

## POWER TRANSISTOR

## SUGGESTED MOUNTING ARRANGEMENT



**NOTE 1:** 0.002" MICA INSULATOR OR ALUMINUM INSULATOR 1/8" THICK, DRILLED OR PUNCHED WITH BURRS REMOVED, AND THEN ANODIZED.

**NOTE 2:** REMOVE BURRS FROM CHASSIS HOLES.

Devices and arrangements shown or described herein may use patents of RCA or others. Information contained herein is furnished without responsibility by RCA for its use and without prejudice to RCA's patent rights.

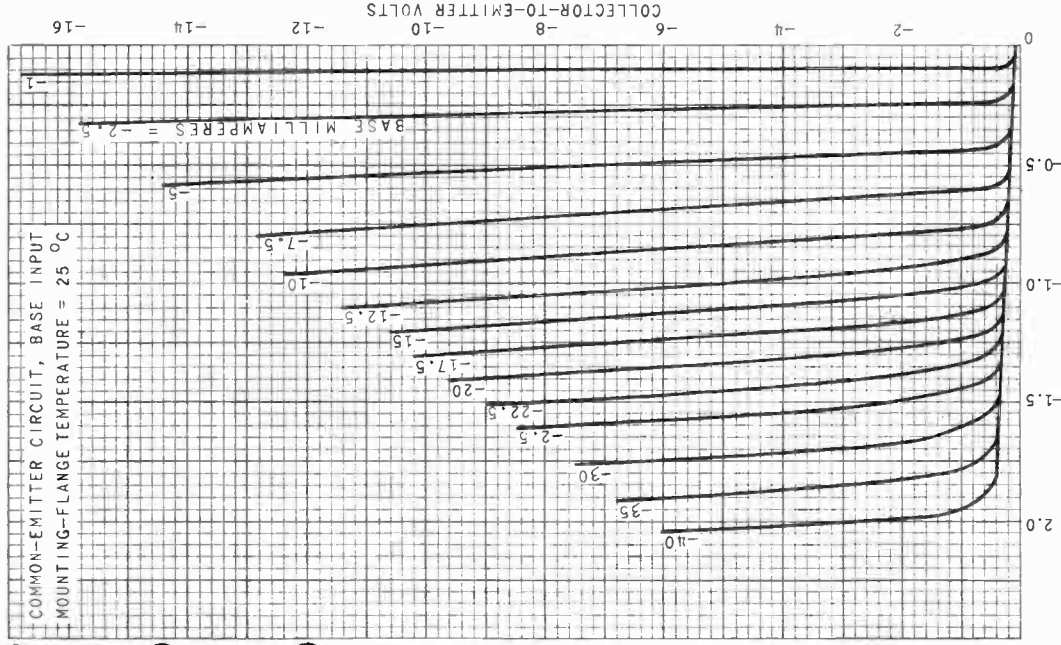




2N301

# AVERAGE COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
MOUNTING-FLANGE TEMPERATURE = 25 °C



2N301

COLLECTOR AMPERES

SEMICONDUCTOR DIVISION

RADIO CORPORATION OF AMERICA, SONNERSVILLE, NEW JERSEY

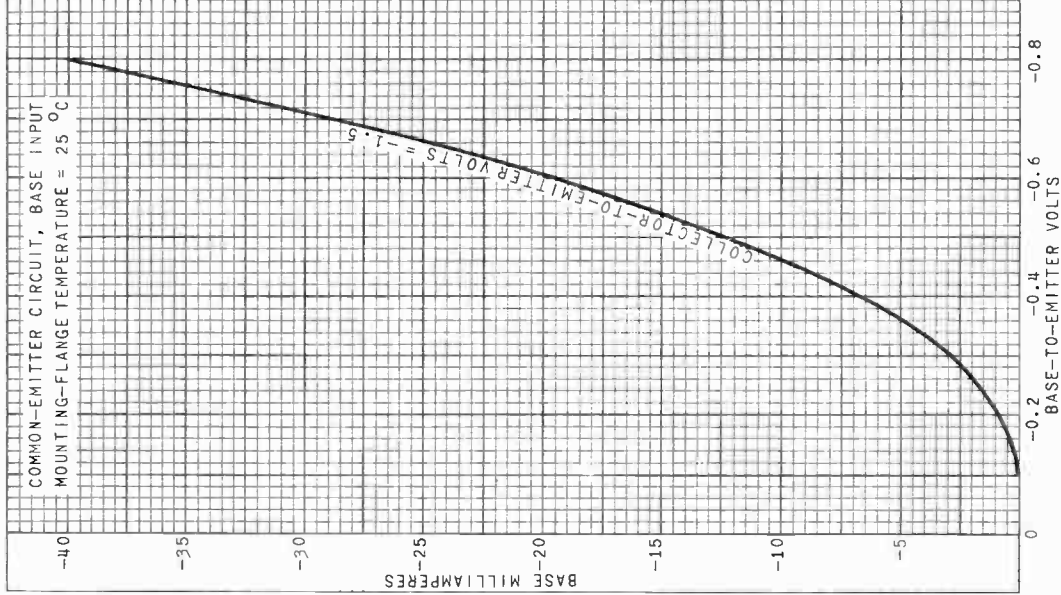
92CS-9247

2N301



2N301

# AVERAGE BASE CHARACTERISTIC

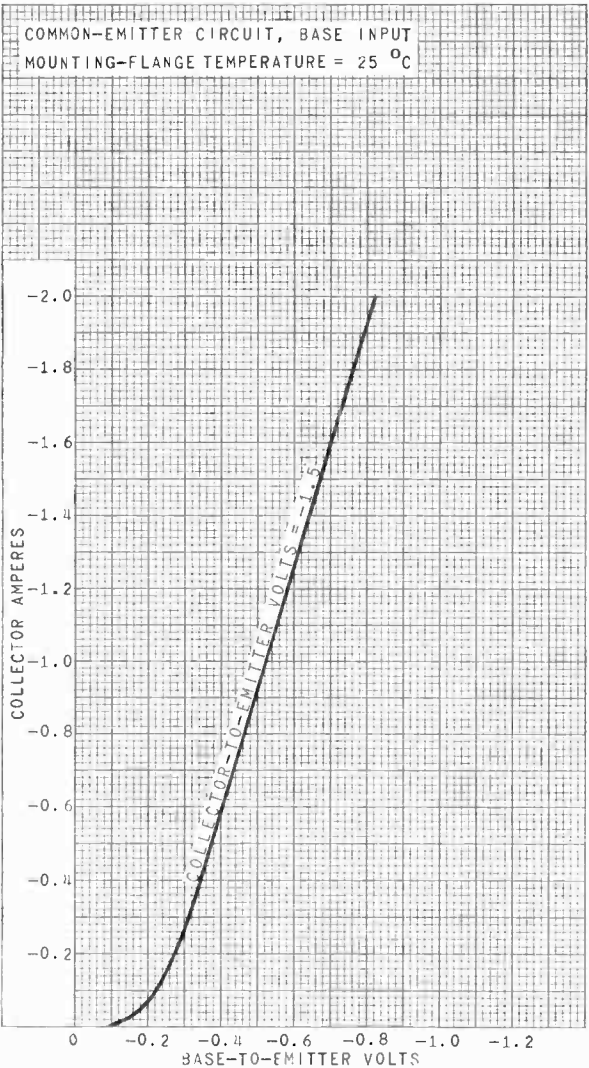




2N301

# AVERAGE TRANSFER CHARACTERISTIC

2N301



SEMICONDUCTOR DIVISION  
RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

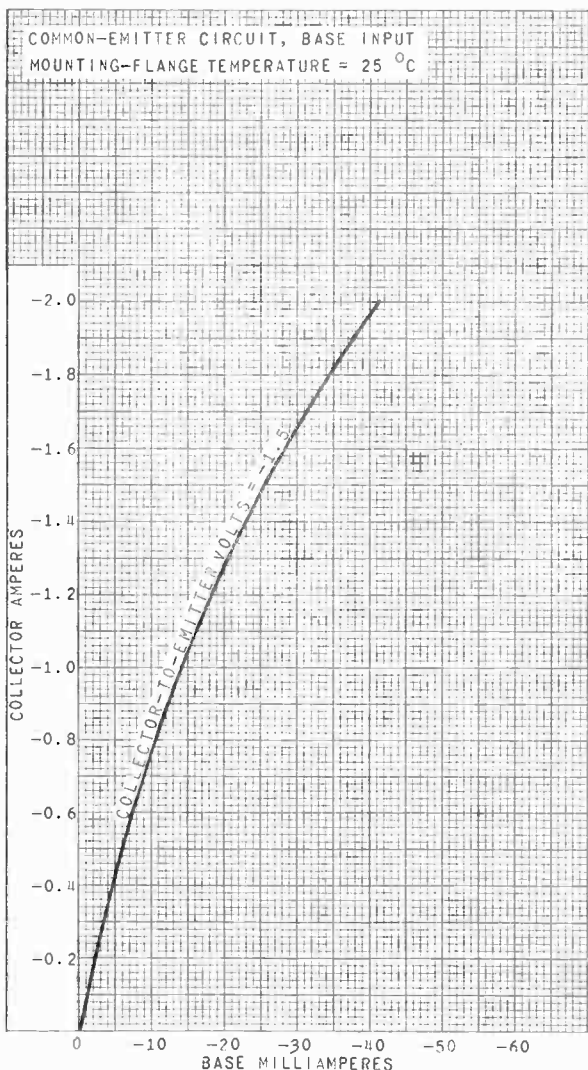
92CS-9249R1

2N301



2N301

## AVERAGE CURRENT-TRANSFER CHARACTERISTIC





2N301-A

# 2N301-A

## POWER TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

*For audio-frequency power applications*

The 2N301-A is the same as the 2N301 except for the following items:

Electrical, For Mounting-Flange Temperature of 25 °C:

Minimum DC Collector-to-Base Voltage for dc collector current of -1 milli- ampere with emitter open . . . . .	-60	volts
---	-----	-------

### AUDIO-FREQUENCY POWER AMPLIFIER -- Class A and Class B

Maximum Ratings, Absolute Values:

PEAK COLLECTOR-TO-BASE VOLTAGE . . . . .	-60 max.	volts
DC COLLECTOR-TO-BASE VOLTAGE (For inductive load). . . . .	-30 max.	volts





2N370

# 2N370

## DRIFT TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For radio-frequency amplifier applications

### GENERAL DATA

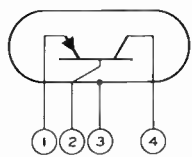
#### Electrical:

Maximum DC Collector Current for dc collector-to-base voltage of -12 volts with emitter open, and at ambient temperature of 25° C . . . . .	-20	μa
Maximum DC Emitter Current for dc emitter-to-base voltage of -1.5 volts with collector open, and at ambient temperature of 25° C . . . . .	-50	μa
Interlead Capacitance between collector and base leads with interlead shield connected to ground and all leads cut to 5/16" . . . . .	0.003	μmf

#### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.375"
Maximum Diameter . . . . .	0.360"
Case . . . . .	Metal
Envelope Seals . . . . .	Hermetic
Leads, Flexible . . . . .	4
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See Dimensional Outline

Lead 1 - Emitter



Lead 3 - Interlead Shield, Metal Case

Lead 4 - Collector

Lead 2 - Base

### RADIO-FREQUENCY AMPLIFIER — Class A

#### Maximum Ratings, Absolute Values:

DC COLLECTOR-TO-BASE VOLTAGE . . . . .	-20 max.	volts
DC EMITTER-TO-BASE VOLTAGE . . . . .	-1.5 max.	volts
DC COLLECTOR CURRENT . . . . .	-10 max.	ma
DC EMITTER CURRENT . . . . .	10 max.	ma
COLLECTOR DISSIPATION:		
At ambient temperature of 25° C . . . . .	80 max.	mw
At ambient temperature of 55° C . . . . .	40 max.	mw
At ambient temperature of 71° C . . . . .	20 max.	mw
AMBIENT TEMPERATURE (During operation) . . . . .	71 max.	°C
STORAGE-TEMPERATURE RANGE . . . . .	-65 to +85	°C



2N370

## DRIFT TRANSISTOR

## Characteristics, At Ambient Temperature of 25° C:

## Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage. . . . .	-12	volts
DC Emitter Current . . . . .	1	ma
Current Transfer Ratio ( $\alpha_f$ ) <sup>■</sup> . . . . .	-60	
Frequency for unity power amplification. . . . .	132	Mc

## Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage . . . . .	-12	volts
DC Emitter Current . . . . .	1	ma
Current Transfer Ratio ( $\alpha_f$ ) <sup>■</sup> . . . . .	0.984	
Frequency at which the current transfer ratio drops to 0.707 times its value at 1 kc. . . . .	30	Mc

## Typical Operation, At Ambient Temperature of 25° C:

## Common-Emitter Circuit, Base Input

At frequency of	1.5	10	20	Mc
DC Collector-to-Emitter Voltage.	-12	-12	-12	volts
DC Emitter Current . . . . .	1	1	1	ma
Input Resistance . . . . .	1750	200	100	ohms
Output Resistance. . . . .	180000	18000	11000	ohms
Maximum Power Gain <sup>▲</sup> . . . . .	50.5	26.2	17	db
Maximum Useful Power Gain (In an unneutralized circuit). . . . .	31	17.6	12.5	db
Intrinsic Transconductance . . . . .	37800	21400	13700	$\mu$ mhos
Collector Transition Capacitance	1.7	1.7	1.7	$\mu$ mf

■ Measured at 1 kc.

▲ Measured in a single-tuned unilateralized circuit matched to the generator and load impedances for maximum transfer of power. Transformer insertion losses not included.

## OPERATING CONSIDERATIONS

The 2N370 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The flexible leads of the 2N370 are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise the heat of the soldering operation will crack the seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using the 2N370, the temperature of the solder should not exceed 230° C for a maximum immersion period of 10 seconds.

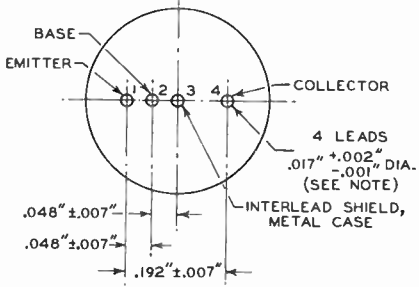
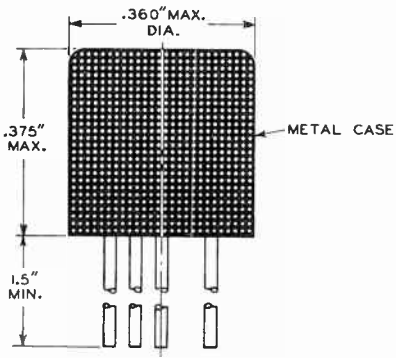




2N370

2N370

# DRIFT TRANSISTOR



92CS-9122R3

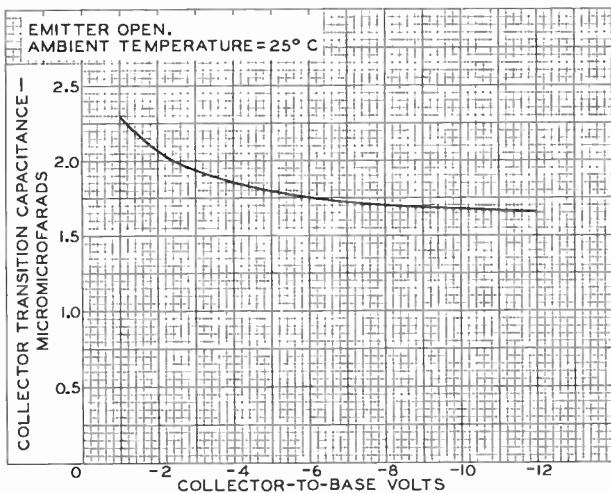
NOTE: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.050" AND 0.250" FROM THE BASE SEAT. BETWEEN 0.250" AND 1.50", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

2N370



2N370

AVERAGE CHARACTERISTIC



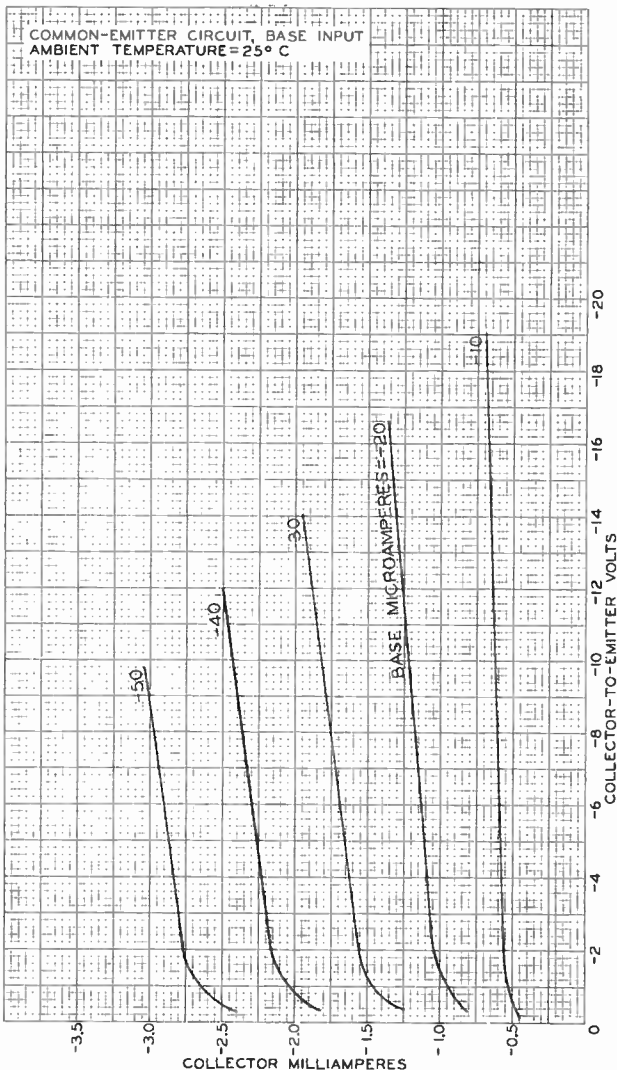
92CS-9527



2N370

2N370

### AVERAGE COLLECTOR CHARACTERISTICS

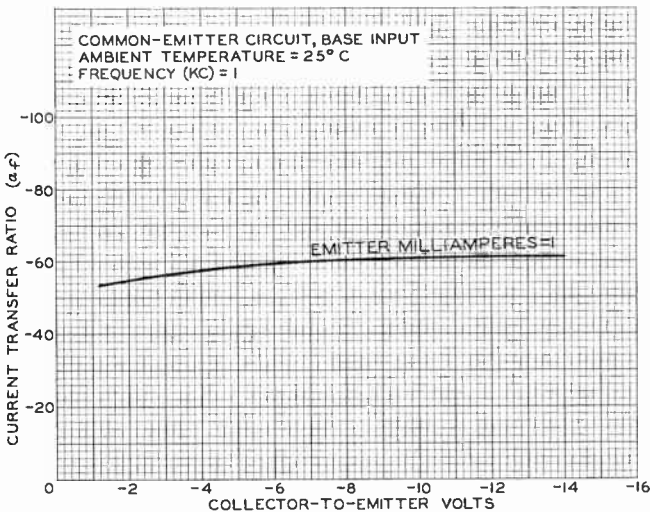
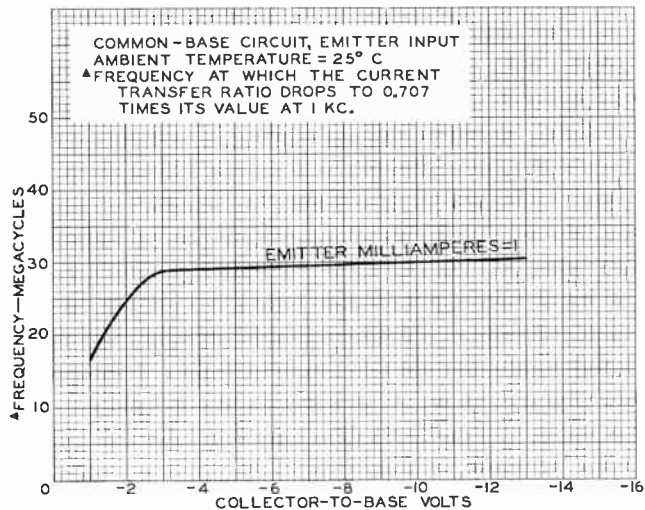


2N370



2N370

## AVERAGE CHARACTERISTICS





2N371

# 2N371

## DRIFT TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For radio-frequency oscillator applications

### GENERAL DATA

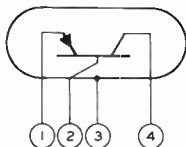
#### Electrical:

Maximum DC Collector Current for dc collector-to-base voltage of -12 volts with emitter open, and at ambient temperature of 25° C . . . . .	-20	μa
Maximum DC Emitter Current for dc emitter-to-base voltage of -0.5 volt with collector open, and at ambient temperature of 25° C . . . . .	-50	μa
Interlead Capacitance between collector and base leads with interlead shield connected to ground and all leads cut to 5/16" . . . . .	0.003	μμf

#### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.375"
Maximum Diameter . . . . .	0.360"
Case . . . . .	Metal
Envelope Seals . . . . .	Hermetic
Leads, Flexible . . . . .	4
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See Dimensional Outline

Lead 1 - Emitter



Lead 3 - Interlead Shield, Metal Case  
Lead 4 - Collector

Lead 2 - Base

### RADIO-FREQUENCY OSCILLATOR

#### Maximum Ratings, Absolute Values:

DC COLLECTOR-TO-BASE VOLTAGE . . . . .	-20 max.	volts
DC EMITTER-TO-BASE VOLTAGE . . . . .	-0.5 max.	volt
DC COLLECTOR CURRENT . . . . .	-10 max.	ma
DC EMITTER CURRENT . . . . .	10 max.	ma
COLLECTOR DISSIPATION:		
At ambient temperature of 25° C . . . . .	80 max.	mw
At ambient temperature of 55° C . . . . .	40 max.	mw
At ambient temperature of 71° C . . . . .	20 max.	mw
AMBIENT TEMPERATURE (During operation) . . . . .	71 max.	°C
STORAGE-TEMPERATURE RANGE . . . . .	-65 to +85	°C

2N371



2N371

## DRIFT TRANSISTOR

Characteristics, At Ambient Temperature of 25° C:

Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage. . . . .	-12	volts
DC Emitter Current. . . . .	1	ma
Current Transfer Ratio ( $\alpha_f$ ) <sup>■</sup> . . . . .	0.984	
Frequency at which the current transfer ratio drops to 0.707 times its value at 1 kc . . . . .	30	Mc

**Typical Operation:**

The 2N371 can produce an oscillator-injection voltage which will provide optimum mixing in a typical rf tuner circuit.

In an oscillator stage utilizing the 2N371 and operating at 22 Mc, if the collector-supply voltage drops from -12 to -8 volts, the frequency provided by this stage will deviate from 22 Mc by less than 7 kc.

■ Measured at 1 kc.

**OPERATING CONSIDERATIONS**

The 2N371 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of the 2N371 are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using the 2N371, the temperature of the solder should not exceed 230° C for a maximum immersion period of 10 seconds.

**DIMENSIONAL OUTLINE and CURVES**  
shown for Type 2N370 also apply to the 2N371



2N372

2N372

## DRIFT TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For radio-frequency mixer applications

## GENERAL DATA

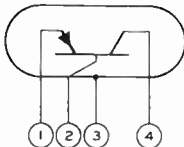
## Electrical:

Maximum DC Collector Current for dc collector-to-base voltage of -12 volts with emitter open, and at ambient temperature of 25° C . . . . .	-20	μa
Maximum DC Emitter Current for dc emitter-to-base voltage of -0.5 volt with collector open, and at ambient temperature of 25° C . . . . .	-50	μa
Interlead Capacitance between collector and base leads with interlead shield connected to ground and all leads cut to 5/16" . . . . .	0.003	μmf

## Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.375"
Maximum Diameter . . . . .	0.360"
Case . . . . .	Metal
Envelope Seals . . . . .	Hermetic
Leads, Flexible . . . . .	4
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See Dimensional Outline

Lead 1 - Emitter



Lead 2 - Base

Lead 3 - Interlead Shield, Metal Case

Lead 4 - Collector

## RADIO-FREQUENCY MIXER

## Maximum Ratings, Absolute Values:

DC COLLECTOR-TO-BASE VOLTAGE . . . . .	-20 max.	volts
DC EMITTER-TO-BASE VOLTAGE . . . . .	-0.5 max.	volt
DC COLLECTOR CURRENT . . . . .	-10 max.	ma
DC EMITTER CURRENT . . . . .	10 max.	ma
COLLECTOR DISSIPATION:		
At ambient temperature of 25° C . . . . .	80 max.	mw
At ambient temperature of 55° C . . . . .	40 max.	mw
At ambient temperature of 71° C . . . . .	20 max.	mw
AMBIENT TEMPERATURE (During operation) . . . . .	71 max.	°C
STORAGE-TEMPERATURE RANGE . . . . .	-65 to +85	°C



2N372

## DRIFT TRANSISTOR

## Characteristics, At Ambient Temperature of 25° C:

## Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage. . . . .	-12	volts
DC Emitter Current . . . . .	1	ma
Current Transfer Ratio ( $\alpha_f$ ) <sup>■</sup> . . . . .	-60	
Frequency for unity power amplification. .	132	Mc

## Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage . . . . .	-12	volts
DC Emitter Current . . . . .	1	ma
Current Transfer Ratio ( $\alpha_f$ ) <sup>■</sup> . . . . .	0.984	
Frequency at which the current transfer ratio drops to 0.707 times its value at 1 kc. . . . .	30	Mc

## Typical Operation, At Ambient Temperature of 25° C:

## Common-Emitter Circuit, Base Input

At frequency of	1.5	10	20	Mc
DC Collector-to-Emitter Voltage.	-12	-12	-12	volts
DC Emitter Current . . . . .	1	1	1	ma
Input Resistance . . . . .	1750	200	100	ohms
Output Resistance. . . . .	180000	18000	11000	ohms
Maximum Power Gain <sup>▲</sup> . . . . .	50.5	26.2	17	db
Maximum Useful Power Gain (In an unneutralized circuit).	31	17.6	12.5	db
Intrinsic Transconductance . . .	37800	21400	13700	$\mu$ mhos
Collector Transition Capacitance.	1.7	1.7	1.7	$\mu$ mf

■ Measured at 1 kc.

▲ Measured in a single-tuned unilateralized circuit matched to the generator and load impedances for maximum transfer of power. Transformer insertion losses not included.

## OPERATING CONSIDERATIONS

The 2N372 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The flexible leads of the 2N372 are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using the 2N372, the temperature of the solder should not exceed 230° C for a maximum immersion period of 10 seconds.

DIMENSIONAL OUTLINE and CURVES  
shown for Type 2N370 also apply to the 2N372



## Drift-Field Transistor

GERMANIUM P-N-P ALLOY TYPE  
For Industrial and Military Applications

### GENERAL DATA

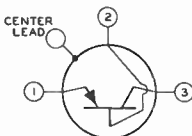
#### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.405"
Maximum Diameter . . . . .	0.240"
Dimensional Outline . . . . .	JEDEC No. TO-44
Case . . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	4
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>

#### Terminal Diagram:

#### BOTTOM VIEW

Lead 1 - Emitter  
Center Lead -  
Interlead  
Shield,  
Case



Lead 2 - Base  
Lead 3 - Collector  
(Adjacent  
to red dot  
on side of  
case)

### INDUSTRIAL SERVICE

*Such as in rf, if, oscillator, mixer, converter, and low-level video-amplifier circuits*

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE (Emitter open) . . . . .	-40 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE (Base-to-emitter volts = 0.5) . . . . .	-40 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-0.5 max.	volt
COLLECTOR CURRENT . . . . .	-10 max.	ma
EMITTER CURRENT . . . . .	10 max.	ma
TRANSISTOR DISSIPATION: <sup>a</sup>		
At ambient temperature of 25° C		
for operation in free air . . . . .	120 max.	mw
At case temperature of 25° C		
for operation with heat sink . . . . .	240 max.	mw
AMBIENT-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +100	°C

#### Typical Operation:

*In accompanying video-amplifier circuit with ambient temperature range of -65 to +55° C*

DC Collector-to-Emitter Voltage . . . . .	-12	volts
DC Emitter Current . . . . .	5.8	ma
Source Impedance . . . . .	150	ohms
Capacitive Load . . . . .	16	μf



# 2N384

## Frequency-Response Range:

Minimum. . . . .	20	cps
Maximum. . . . .	10	Mc
Pulse-Rise Time. . . . .	0.035	$\mu$ sec
Voltage Gain . . . . .	26	db
Maximum Peak-to-Peak Output Voltage. . . . .	20	volts

<sup>a</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## CHARACTERISTICS RANGE VALUES FOR EQUIPMENT DESIGN

Voltage values are given with respect to base unless otherwise specified. Ambient temperature = 25° C.

Min. Typical Max.

### DC Collector Breakdown

Voltage for dc collector

$\mu$ a = -50, dc emitter

ma. = 0. . . . .  $BV_{CBO}$  -40 -80 - volts

### Punch-Through Voltage for

dc emitter volts = -0.5.

$V_p$  -40 -80 - volts

### DC Collector-Cutoff Current

for dc collector volts =

-12, dc emitter ma. = 0.

$I_{CBO}$  - -4 -12  $\mu$ a

### DC Emitter-Cutoff Current

for dc emitter volts =

-0.5, collector open . . .

$I_{EBO}$  - -1 -12  $\mu$ a

### Small-Signal Current Trans-

fer Ratio for dc collec-

tor-to-emitter volts =

-12, dc emitter ma. = 1.5,

signal frequency of 1 kc.  $h_{fe}$  20 60 175

### → Alpha-Cutoff Frequency for

dc collector volts = -12,

dc emitter ma. = 1.5 . . .

$f_{\alpha b}$  - 100 - Mc

### Input Resistance:<sup>b</sup>

With dc collector volts

= -12, dc emitter ma. =

1.5, signal frequency

of 50 Mc . . . . .

$R_{in}$  - 30 - ohms

With dc collector-to-

emitter volts = -12, dc

emitter ma. = 1.5, sig-

nal frequency of 30 Mc .

- 50 - ohms

With dc collector-to-

emitter volts = -12, dc

emitter ma. = 1.5, sig-

nal frequency of 12.5 Mc.

- 250 - ohms

### Output Resistance:<sup>c</sup>

With dc collector volts

= -12, dc emitter ma.

= 1.5, signal fre-

quency of 50 Mc. . . . .

$R_{out}$  - 5000 - ohms

→ Indicates a change.



With dc collector-to-emitter volts = -12, dc emitter ma. = 1.5, signal frequency of 30 Mc. . . . .	-	5000	-	ohms
With dc collector-to-emitter volts = -12, dc emitter ma. = 1.5, signal frequency of 12.5 Mc. . . . .	-	16000	-	ohms
Collector-to-Base Capacitance for dc collector volts = -12, dc emitter ma. = 0. . . . .	$C_{ob}$	2	3	$\mu\mu f$
Power Gain: <sup>d</sup>	PG			
With dc collector volts = -12, dc emitter ma. = 1.5, signal frequency of 50 Mc. . . . .		15	18	21
With dc collector-to-emitter volts = -12, dc emitter ma. = 1.5, signal frequency of 30 Mc. . . . .		16	20	24
With dc collector-to-emitter volts = -12, dc emitter ma. = 1.5, signal frequency of 12.5 Mc. . . . .		24	28	32
Thermal Resistance: <sup>b</sup>	$R_T$			
Between junction and case . . . . .		-	-	0.31 °C/watt
Between junction and free air . . . . .		-	-	0.62 °C/watt

<sup>b</sup> AC output-circuit shorted.

<sup>c</sup> AC input-circuit shorted.

<sup>d</sup> Measured in a single-tuned unilateralized circuit matched to the generator and load impedance for maximum transfer of power (transformer-insertion losses not included).

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.

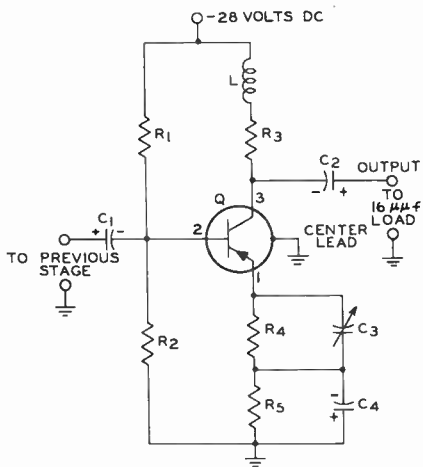


# 2N384

When dip soldering is employed in the assembly of printed circuitry using this transistor, the temperature of the solder should not exceed  $255^{\circ}\text{C}$  for a maximum immersion period of 10 seconds.

This transistor utilizes shielding to minimize interlead capacitance and coupling to adjacent circuit components. This shielding is provided by a fourth lead which is internally connected to the case. For optimum performance, it is recommended that this lead be connected to the chassis ground.

## VIDEO-AMPLIFIER CIRCUIT



92CS-10394R1

- $C_1$ : 25  $\mu\text{f}$ , 12 volts
- $C_2$ : 25  $\mu\text{f}$ , 25 volts
- $C_3$ : 100 to 300  $\mu\text{f}$  (variable)
- $C_4$ : 100  $\mu\text{f}$ , 12 volts
- L: 30  $\mu\text{h}$
- Q: Transistor type 2N384
- $R_1$ : 20,000 ohms, 0.25 watt
- $R_2$ : 3600 ohms, 0.25 watt
- $R_3$ : 2000 ohms, 0.25 watt
- $R_4$ : 62 ohms, 0.25 watt
- $R_5$ : 620 ohms, 0.25 watt

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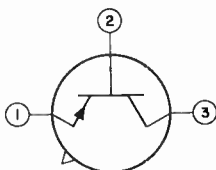
## Transistor

GERMANIUM P-N-P ALLOY-JUNCTION TYPE

For "On-Off" Control Applications  
in Industrial and Military EquipmentThe 2N398B is a Direct Replacement for Type 2N398

## GENERAL DATA

## Mechanical:

Dimensions. . . . . See Outline T0-5 in General Section  
Terminal Diagram: BOTTOM VIEWLead 1 - Emitter  
Lead 2 - Base

Lead 3 - Collector

## SWITCHING SERVICE

For direct "on-off" control of high-voltage, low-power devices such as neon indicators, relays, incandescent-lamp indicators, and indicating counters of electronic computers

Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE:			
With emitter open . . . . .	$V_{CBO}$	-105 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:			
With base short-circuited to emitter. . . . .	$V_{CES}$	-105 max.	volts
EMITTER-TO-BASE VOLTAGE:			
With collector open . . . . .	$V_{EBO}$	-50 max.	volts
COLLECTOR CURRENT . . . . .	$I_C$	-100 max.	ma
EMITTER CURRENT . . . . .	$I_E$	100 max.	ma
TRANSISTOR DISSIPATION:			
At free-air temperatures:			
From -65° to 25° C. . . . .		50 max.	mw
At 55° C. . . . .		10 max.	mw
TEMPERATURE RANGE:			
Operating . . . . .	$T_{OPR}$	-65 to 55	°C
Storage . . . . .	$T_{STG}$	-65 to 85	°C
LEAD TEMPERATURE: <sup>a</sup>			
For 10 seconds maximum. . . . .	$T_L$	230 max.	°C

<sup>a</sup> Measured 1/16" ± 1/32" along lead down from seating plane.

← Indicates a change.



## ELECTRICAL CHARACTERISTICS

Free-air temperature = 25° C

		Min.	Max.	
DC Collector-to-Emitter Reach-Through Voltage <sup>b</sup> . . . . .	$V_{RT}$	-105	-	volts
DC Collector-to-Base Breakdown Voltage for dc collector ma. = -0.05, emitter current = 0. . . . .	$BV_{CBO}$	-105	-	volts
DC Emitter-to-Base Breakdown Voltage for dc emitter ma. = -0.05, collector current = 0. . . . .	$BV_{EBO}$	-50	-	volts
DC Base-to-Emitter Saturation Voltage for dc collector ma. = -5, dc base ma. = -0.25 . . . . .	$V_{BE}(sat)$	-	-0.4	volt
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = -5, dc base ma. = -0.25 . . . . .	$V_{CE}(sat)$	-	-0.35	volt
DC Collector-Cutoff Current: For emitter current = 0, dc collector-to-base volts = -2.5 . . . . .	$I_{CBO}$	-	-14	$\mu a$
		-	-50	$\mu a$
→ DC Collector Current for dc collector-to-emitter voltage = -105, base short-circuited to emitter. . . . .	$I_{CES}$	-	-600	$\mu a$
DC Emitter-Cutoff Current for dc emitter-to-base volts = -50, collector current = 0. . . . .	$I_{EBO}$	-	-50	$\mu a$
DC Forward-Current Transfer Ratio for dc collector-to-emitter volts = -0.35, dc collector ma. = -5 . . . . .	$h_{FE}$	20	-	

<sup>b</sup> The dc collector-to-emitter reach-through voltage is determined by connecting a high-impedance voltmeter (11 megohms or greater) between the emitter and base, and measuring the collector-to-base voltage which causes the emitter to assume an emitter-to-base floating voltage of -1 volt.

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The flexible leads of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the seating plane provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the seals of the leads and damage the transistor.

→ Indicates a change.





2N398

2N398

# JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

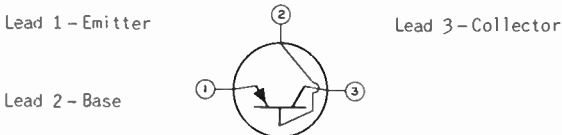
For high-voltage "on-off" control applications

## GENERAL DATA

### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.250"
Maximum Diameter . . . . .	0.360"
Case . . . . .	Metal
Envelope Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See Dimensional Outline

### BOTTOM VIEW



## SWITCHING SERVICE

### Maximum Ratings, Absolute Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	-105 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE . . . . .	-105 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-50 max.	volts
COLLECTOR CURRENT . . . . .	-100 max.	ma
EMITTER CURRENT . . . . .	100 max.	ma
TRANSISTOR DISSIPATION:		
At ambient temperature of 25° C . . . . .	50 max.	mw
At ambient temperature of 55° C . . . . .	10 max.	mw
AMBIENT TEMPERATURE (During operation) . . . . .	55 max.	°C
STORAGE-TEMPERATURE RANGE . . . . .	-65 to +85	°C

## CHARACTERISTICS RANGE VALUES FOR EQUIPMENT DESIGN

Voltage values are given with respect to the base unless otherwise specified. Ambient temperature = 25° C.

	Typical Values	Range Values		
		Min.	Max.	
DC Collector Breakdown Voltage ( $V_{CB0}$ ) with dc collector current ( $I_C$ ) = -50 $\mu$ a, dc emitter current ( $I_E$ ) = 0 . . . . .	-150	-105	-	volts
DC Collector Cutoff Current ( $I_{CB0}$ ) with dc collector voltage ( $V_C$ ) = -2.5 volts, dc emitter current ( $I_E$ ) = 0 . . . . .	-6	-	-14	$\mu$ a



2N398

## JUNCTION TRANSISTOR

	Typical Values	Range Values		
		Min.	Max.	
DC Emitter Breakdown Voltage ( $BV_{EBO}$ ) with dc emitter current ( $I_E$ ) = $-50 \mu\text{a}$ , dc collector current ( $I_C$ ) = 0 .	-75	-50	-	volts
DC Collector-to-Emitter (Punch-Through) Voltage* . .	-150	-105	-	volts
DC Collector-to-Emitter Saturation Voltage ( $V_{CE}$ ) with dc collector current ( $I_C$ ) = $-5 \text{ ma.}$ , dc base current ( $I_B$ ) = $0.25 \text{ ma.}$ . . . .	-0.20	-	-0.35	volt
DC Base-to-Emitter Saturation Voltage ( $V_{BE}$ ) with dc collector current ( $I_C$ ) = $-5 \text{ ma.}$ , dc base current ( $I_B$ ) = $-0.25 \text{ ma.}$ . . . . .	-0.30	-	-0.40	volt
Large-Signal DC Current Transfer Ratio ( $\alpha_{fe}$ ) with dc collector current ( $I_C$ ) = $-5 \text{ ma.}$ , dc collector-to- emitter voltage ( $V_{CE}$ ) = $-0.35 \text{ volt}$ . . . . .	60	20	-	

\* The dc collector-to-emitter (punch-through) voltage is determined by connecting a high-impedance voltmeter (11 megohms or greater) between the emitter and base and measuring the collector-to-base voltage which causes the emitter to assume an emitter-to-base floating voltage of  $-1 \text{ volt}$ .

## OPERATING CONSIDERATIONS

The 2N398 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of the 2N398 are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using the 2N398, the temperature of the solder should not exceed  $230^\circ \text{C}$  for a maximum immersion period of 10 seconds.

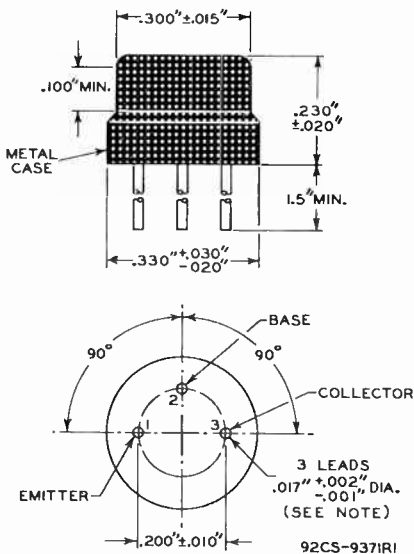




2N398

2N398

# JUNCTION TRANSISTOR



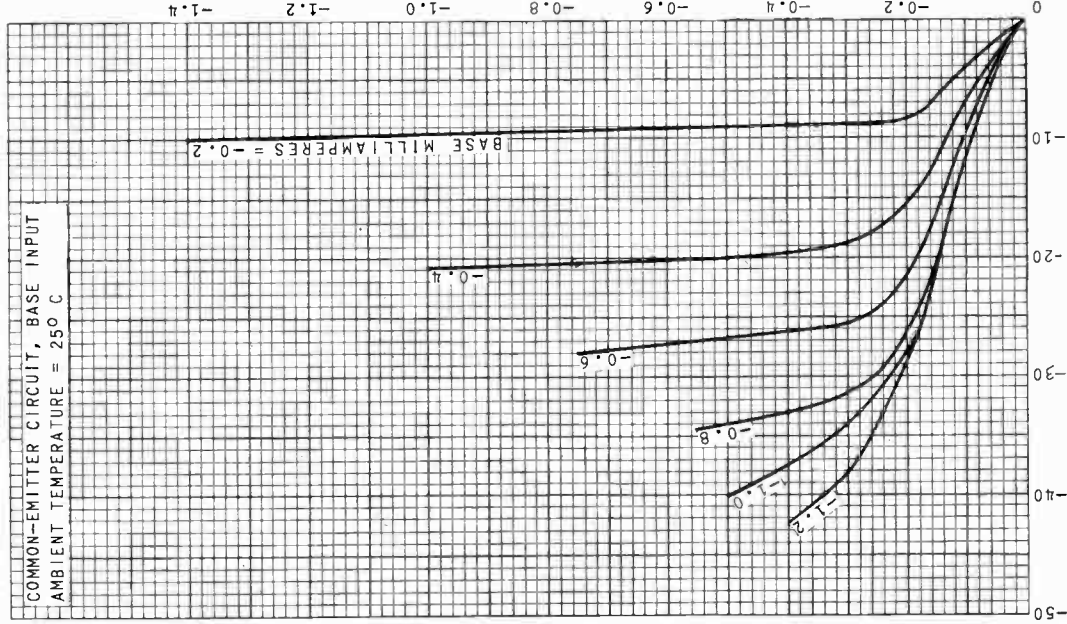
NOTE: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.050" AND 0.250" FROM THE PLANE OF THE ACTUAL BOTTOM OF THE BASE. BETWEEN 0.250" AND 1.50", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.



2N398

# AVERAGE COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE = 250 C



2N398

World Precision Instrument

COLLECTOR MILLIAMPERES  
SEMICONDUCTOR DIVISION

RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

92CS-9382

COLLECTOR-TO-EMITTER VOLTS

0 -0.2 -0.4 -0.6 -0.8 -1.0 -1.2 -1.4

# 2N398A

## Transistor

GERMANIUM P-N-P ALLOY-JUNCTION TYPE

For "On-Off" Control Applications  
in Industrial and Military Equipment

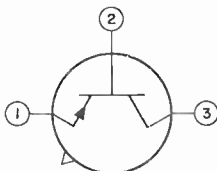
The 2N398B is a Direct Replacement for Type 2N398A

### GENERAL DATA

#### Mechanical:

Dimensions . . . . . See Outline TO-5 in General Section  
Terminal Diagram: ←  
BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector

### SWITCHING SERVICE

For direct "on-off" control of high-voltage, low-power devices such as neon indicators, relays, incandescent-lamp indicators, and indicating counters of electronic computers

Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE:			
With emitter open . . . . .	$V_{CBO}$	-105 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:			
With base short-circuited to emitter. . . . .	$V_{CES}$	-105 max.	volts ←
EMITTER-TO-BASE VOLTAGE:			
With collector open . . . . .	$V_{EBO}$	-50 max.	volts
COLLECTOR CURRENT . . . . .	$I_C$	-200 max.	ma
EMITTER CURRENT . . . . .	$I_E$	200 max.	ma
TRANSISTOR DISSIPATION: $P_T$			
At free-air temperatures:			
From -65° to 25° C. . . . .		150 max.	mw
Above 25° C. . . . .		Derate linearly 2 mw/°C	
TEMPERATURE RANGE:			
Operating . . . . .	$T_{OPR}$	-65 to 100	°C
Storage . . . . .	$T_{STG}$	-65 to 100	°C
LEAD TEMPERATURE: <sup>a</sup>			
For 3 seconds maximum . . . . .	$T_L$	250 max.	°C

<sup>a</sup> Measured 1/16" ± 1/32" along lead down from seating plane.

← indicates a change.



# 2N398A

## ELECTRICAL CHARACTERISTICS

Free-air temperature = 25° C

		Min.	Max.	
DC Collector-to-Emitter Reach-Through Voltage <sup>b</sup> . . . . .	$V_{RT}$	-105	-	volts
DC Collector-to-Base Breakdown Voltage for dc collector ma. = -0.05, emitter current = 0. . . . .	$BV_{CBO}$	-105	-	volts
DC Emitter-to-Base Breakdown Voltage for dc emitter ma. = -0.05, collector current = 0. . . . .	$BV_{EBO}$	-50	-	volts
DC Base-to-Emitter Saturation Voltage for dc collector ma. = -5, dc base ma. = -0.25 . . . . .	$V_{BE}(sat)$	-	-0.4	volt
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = -5, dc base ma. = -0.25 . . . . .	$V_{CE}(sat)$	-	-0.35	volt
DC Collector-Cutoff Current for emitter current = 0, dc collector-to-base volts = -2.5 . . . . .	$I_{CBO}$	-	-14	$\mu a$
		-	-50	$\mu a$
→ DC Collector Current for dc collector-to-emitter voltage = -105, base short-circuited to emitter. . . . .	$I_{CES}$	-	-600	$\mu a$
DC Emitter-Cutoff Current for dc emitter-to-base volts = -50, collector current = 0. . . . .	$I_{EBO}$	-	-50	$\mu a$
DC Forward-Current Transfer Ratio for dc collector-to-emitter volts = -0.35, dc collector ma. = -5. . . . .	$h_{FE}$	20	-	
Small-Signal Short-Circuit Forward-Current Transfer Ratio for dc collector-to-emitter volts = -6, dc collector ma. = -1, frequency (kc) = 1. . . . .	$h_{fe}$	20	-	
Thermal Resistance:				
Junction-to-free air . . . . .	$\theta_{JFA}$	-	0.5	°C/mw

<sup>b</sup> The dc collector-to-emitter reach-through voltage is determined by connecting a high-impedance voltmeter (11 megohms or greater) between the emitter and base, and measuring the collector-to-base voltage which causes the emitter to assume an emitter-to-base floating voltage of -1 volt.

→ Indicates a change.



## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the seating plane provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the seals of the leads and damage the transistor.





# 2N398A

## Transistor

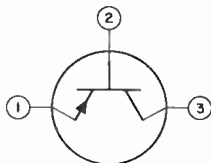
GERMANIUM P-N-P ALLOY-JUNCTION TYPE  
For "On-Off" Control Applications

### GENERAL DATA

#### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter . . . . .	0.370"
Dimensional Outline . . . . .	JEDEC No. TO-5
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector

### SWITCHING SERVICE

*For direct high-voltage control of "on-off" devices such as neon indicators, relays, incandescent-lamp indicators, and indicating counters of electronic computers*

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

##### COLLECTOR-TO-BASE VOLTAGE:

With emitter open . . . . . -105 max. volts

##### COLLECTOR-TO-EMITTER VOLTAGE:

With base open . . . . . -105 max. volts

##### EMITTER-TO-BASE VOLTAGE:

With collector open . . . . . -50 max. volts

COLLECTOR CURRENT . . . . . -200 max. ma

EMITTER CURRENT . . . . . 200 max. ma

##### TRANSISTOR DISSIPATION:<sup>a</sup>

At free-air temperature of  
25° C or below . . . . . 150 max. mw

##### FREE-AIR TEMPERATURE RANGE:

Operating and storage . . . . . -65 to +100 °C

##### LEAD TEMPERATURE:

For 3 seconds maximum<sup>b</sup> . . . . . 250 max. °C

<sup>a</sup> See accompanying Rating Chart.

<sup>b</sup> Measured 1/16" ± 1/32" down from seating plane.



# 2N398A

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base unless otherwise specified. Free-air temperature of 25° C.

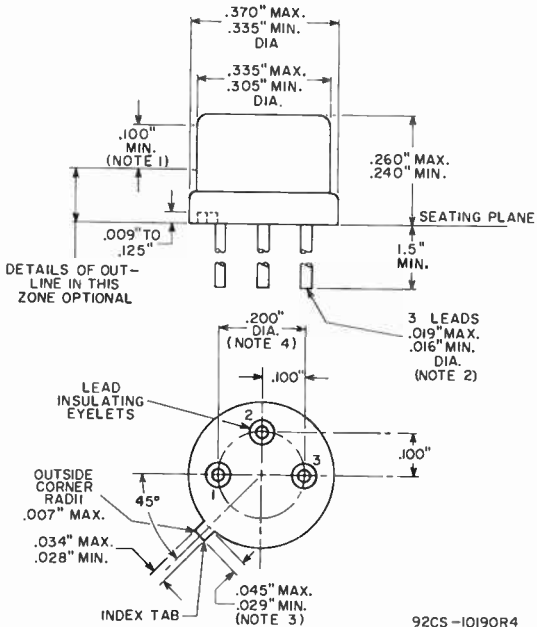
		Min.	Max.	
DC Collector-to-Emitter Reach-Through Voltage <sup>c</sup> . . . . .	$V_{RT}$	-105	-	volts
DC Base-to-Emitter Saturation Voltage for dc collector ma. = -5, dc base ma. = 0.25. . . . .	$V_{BE}(sat)$	-	-0.4	volt
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = -5, dc base ma. = -0.25 . . . . .	$V_{CE}(sat)$	-	-0.35	volt
DC Collector-Cutoff Current for dc emitter ma. = 0, dc collector-to-base volts = -2.5. . . . .	$I_{CBO}$	-	-14	$\mu a$
		-	-50	$\mu a$
DC Emitter-Cutoff Current for dc emitter volts = -50, dc collector ma. = 0 . . . . .	$I_{EBO}$	-	-50	$\mu a$
DC Current Transfer Ratio for dc collector-to-emitter volts = -0.35, dc collector ma. = -5. . . . .	$h_{FE}$	20	-	
Small-Signal Current Transfer Ratio for dc collector-to-emitter volts = -6, dc collector ma. = -1. . . . .	$h_{fe}$	20	-	
Thermal Resistance: Junction-to-free air. . . . .	$\theta_{J-FA}$	-	0.5	°C/mw

<sup>c</sup> The dc collector-to-emitter reach-through voltage is determined by connecting a high-impedance voltmeter (11 megohms or greater) between the emitter and base, and measuring the collector-to-base voltage which causes the emitter to assume an emitter-to-base floating voltage of -1 volt.





JEDEC No. T0-5



**NOTE 1:** THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE VARIATION IN ACTUAL DIAMETER WITHIN THE ZONE SHALL NOT EXCEED 0.010".

**NOTE 2:** THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE SEATING PLANE. BETWEEN 0.25" AND 1.5", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

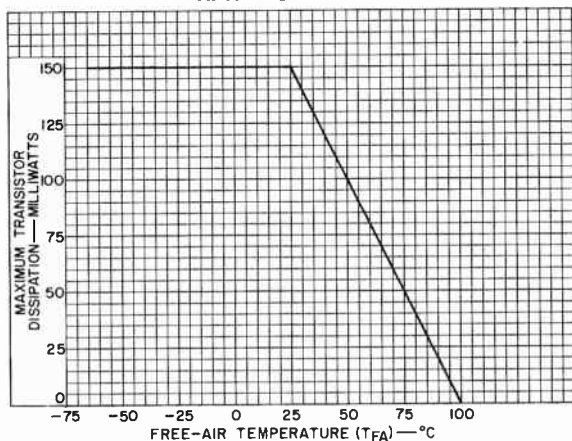
**NOTE 3:** MEASURED FROM MAXIMUM DIAMETER OF THE ACTUAL DEVICE.

**NOTE 4:** LEADS HAVING MAXIMUM DIAMETER (0.019") MEASURED IN GAUGING PLANE OF 0.054" + 0.001" - 0.000" BELOW THE SEATING PLANE OF THE DEVICE SHALL BE WITHIN 0.007" OF THEIR TRUE LOCATIONS RELATIVE TO A MAXIMUM-WIDTH TAB.



# 2N398A

## RATING CHART



92CS-11366



# 2N398B

## Transistor

GERMANIUM P-N-P ALLOY-JUNCTION TYPE

For "On-Off" Control Applications in Industrial and Military Equipment

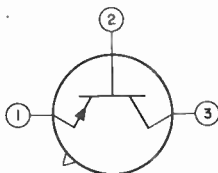
The 2N398B is Unilaterally Interchangeable with Types 2N398 and 2N398A

### GENERAL DATA

#### Mechanical:

Dimensions. . . . . See Outline TO-5 in General Section  
Terminal Diagram: BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector

### SWITCHING SERVICE

For direct "on-off" control of high-voltage, low-power devices such as neon indicators, relays, incandescent-lamp indicators, and indicating counters of electronic computers

Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE:

With emitter open . . . . .  $V_{CB0}$  -105 max. volts

COLLECTOR-TO-EMITTER VOLTAGE:

With base short-circuited to emitter. . . . .  $V_{CES}$  -105 max. volts

EMITTER-TO-BASE VOLTAGE:

With collector open . . . . .  $V_{EBO}$  -75 max. volts

COLLECTOR CURRENT . . . . .  $I_C$  -200 max. ma

EMITTER CURRENT . . . . .  $I_E$  200 max. ma

TRANSISTOR DISSIPATION:  $P_T$

At free-air temperatures:

From -65° to 25° C. . . . . 250 max. mw

Above 25° C. . . . . Derate linearly 3.33 mw/°C

TEMPERATURE RANGE:

Operating . . . . .  $T_{OPR}$  -65 to 100 °C

Storage . . . . .  $T_{STG}$  -65 to 100 °C

LEAD TEMPERATURE:<sup>a</sup>

For 10 seconds maximum. . . . .  $T_L$  250 max. °C

<sup>a</sup> Measured 1/16" ± 1/32" along lead down from seating plane.



# 2N398B

## ELECTRICAL CHARACTERISTICS

Unless otherwise specified, free-air temperature = 25° C

		Min.	Max.	
DC Collector-to-Emitter Reach-Through Voltage <sup>b</sup> . . . . .	$V_{RT}$	-105	-	volts
DC Collector-to-Base Breakdown Voltage for dc collector ma. = -0.025, emitter current = 0 . . . . .	$BV_{CBO}$	-105	-	volts
DC Emitter-to-Base Breakdown Voltage for dc emitter ma. = -0.05, collector current = 0 . . . . .	$BV_{EBO}$	-75	-	volts
DC Base-to-Emitter Saturation Voltage for dc collector ma. = -5, dc base ma. = -0.25 . . . . .	$V_{BE(sat)}$	-	-0.3	volt
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = -5, dc base ma. = -0.25 . . . . .	$V_{CE(sat)}$	-	-0.25	volt
DC Collector-Cutoff Current: With dc collector-to-base volts = -2.5, emitter current = 0 . . . . .	$I_{CBO}$	-	-6	$\mu a$
With dc collector-to-base volts = -105, emitter current = 0, free-air temperature = 25° C . . . . .		-	-25	$\mu a$
71° C . . . . .		-	-300	$\mu a$
DC Collector Current for dc collector-to-emitter voltage = -105, base short-circuited to emitter . . . . .	$I_{CES}$	-	-300	$\mu a$
DC Collector Current for dc collector-to-emitter volts = -55, base-to-emitter resistance (ohms) = 10000 . . . . .	$I_{CER}$	-	-300	$\mu a$
DC Emitter-Cutoff Current for collector current = 0, dc emitter-to-base volts = -2.5 . . . . .	$I_{EBO}$	-	-6	$\mu a$
-75 . . . . .		-	-50	$\mu a$
DC Forward-Current Transfer Ratio for dc collector-to-emitter volts = -0.25, dc collector ma. = -5 . . . . .	$h_{FE}$	20	-	
Small-Signal Short-Circuit Forward-Current Transfer Ratio for dc collector-to-emitter volts = -6, dc collector ma. = -1, frequency (kc) = 1 . . . . .	$h_{fe}$	40	-	

<sup>b</sup> The dc collector-to-emitter reach-through voltage is determined by connecting a high-impedance voltmeter (11 megohms or greater) between the emitter and base, and measuring the collector-to-base voltage which causes the emitter to assume an emitter-to-base floating voltage of -1 volt.



	Min.	Max.	
Small-Signal Short-Circuit Forward-Current Transfer Ratio Cutoff Frequency for dc collector-to-base volts = -6, dc emitter ma. = 1 . . . . .	$f_{hfb}$	1	- Mc
Thermal Resistance:			
Junction-to-free air. . . . .	$\theta_{JFA}$	-	0.3 °C/mw

### PERFORMANCE TESTS AND SPECIAL RATINGS

This transistor type is tested in strict accordance with rigid procedures conforming to the environmental, life, and mechanical requirements of Military Specification MIL-S-19500B.

#### Moisture Resistance:

This test is performed on a sample lot of transistors from each production run. The transistors are subjected to temperature cycling during this moisture-resistance test to provide alternate periods of condensation and drying. Increased effectiveness is also obtained by the use of a high temperature which intensifies the effects of humidity. At the end of the test, the transistors in the sample lot are required to meet the limits for  $BV_{CB0}$ ,  $BV_{EB0}$ , and  $h_{FE}$  as shown under *Characteristics Endpoint Values*.

#### Salt Atmosphere:

This test is performed on a sample lot of transistors from each production run. The transistors are placed in a test chamber through which a salt atmosphere fog (at a temperature of 35° C) is passed for 24 + 2 - 0 hours. The fog concentration and velocity are adjusted so that the rate of salt deposition in the test area is 10000 to 50000 mg/meter<sup>2</sup>/day. At the end of the test, the transistors in the sample lot are required to meet the limits for  $BV_{CB0}$ ,  $BV_{EB0}$ , and  $h_{FE}$  as shown under *Characteristics Endpoint Values*.

#### Temperature Cycling:

Cycles of Intermittent Operation. . . . . 10 min. cycles

This test is performed on a sample lot of transistors from each production run. The transistors undergo 10 temperature cycles from -65 ± 3° C to + 100 ± 3° C. At the end of the test, the transistors in the sample lot are required to meet the established limits for  $I_{CB0}$  and  $h_{FE}$  as shown under *Characteristics Endpoint Values*.

#### Thermal Shock:

Temperature Extremes. . . . . +100 to 0 °C

This test is performed on a sample lot of transistors from each production run. The transistors are completely immersed in water at a high temperature (100 ± 3° C) for not less than 15 seconds and then are immediately plunged into water at a low temperature (0 ± 3° C). At the end of the test, the transistors in the sample lot are required to meet the limits for  $I_{CB0}$  and  $h_{FE}$  as shown under *Characteristics Endpoint Values*.



# 2N398B

## Operating Life Performance:

This test is performed on a sample lot of transistors from each production run. The transistors are operated at a transistor dissipation of 150 mw (with  $V_{CC} = -100$  v) in the accompanying *Operating-Life Test Circuit*, and at a free-air temperature of  $25 \pm 3^{\circ}$  C. At the end of 1000 hours, the transistors in the sample lot are required to meet the limits for  $I_{CBO}$ ,  $h_{FE}$ ,  $BV_{CBO}$ , and  $BV_{EBO}$  as shown under *Characteristics Endpoint Values*.

## Storage Life Performance (High Temperature):

This test is performed on a sample lot of transistors from each production run. The transistors are placed in a chamber at a temperature of  $100 \pm 3^{\circ}$  C for a period of 1000 hours. At the end of 1000 hours, the transistors in the sample lot are required to meet the limits for  $I_{CBO}$ ,  $h_{FE}$ ,  $BV_{CBO}$ , and  $BV_{EBO}$  as shown under *Characteristics Endpoint Values*.

## Constant Acceleration:

Centrifugal Acceleration. . . . . 10000 max. g

This test is performed on a sample lot of transistors from each production run. The transistors are rigidly mounted with suitable protection for the leads. A centrifugal acceleration of 10000 g is applied to the transistors for one minute in each of the orientations  $X_1$ ,  $Y_1$ , and  $Z_1$ . The acceleration is increased to 10000 g in not less than 20 seconds and then decreased gradually to zero in not less than 20 seconds. At the end of the test, the transistors in the sample lot are required to meet the limits for  $BV_{CBO}$ ,  $BV_{EBO}$ , and  $h_{FE}$  as shown under *Characteristics Endpoint Values*.

## Lead Fatigue:

Two leads of each transistor in the sample lot are subjected to a pull of  $16 \pm 1$  ounces for three  $90^{\circ}$  arcs of the case (movement of the case, without torsion, to a position perpendicular to the pull axis and return to normal). All arcs on a single lead are in the same direction and in the same plane. The lead under test is restricted so that the bend starts  $3/32 \pm 1/32$  inch from the case. Breakage of one or more of the leads under these test conditions constitutes failure.

## Shock:

Impact Acceleration . . . . . 1500 max. g

This test is performed on a sample lot of transistors from each production run. The transistors are rigidly mounted with suitable protection for the leads. An impact of 1500 g maximum is applied to the transistors by means of an impact testing machine. During this test, the transistors are subjected to five blows each with an acceleration of 1500 g and a duration of approximately 0.5msec, in each of the orientations  $X_1$ ,  $Y_1$ ,  $Y_2$ , and  $Z_1$ . At the end of the test, the transistors in the sample lot are required to meet the limits for  $BV_{CBO}$ ,  $BV_{EBO}$ , and  $h_{FE}$  as shown under *Characteristics Endpoint Values*.



**Solderability:**

This test is performed on a sample lot of transistors from each production run. The transistor leads are immersed in a flux composed of 25% (by weight) water-white resin and 75% isopropyl alcohol (90%) for a minimum of 5 seconds and then are dipped into molten solder (60% tin, and 40% lead, at  $230 \pm 5^\circ \text{C}$ ) for  $5 \pm 1/2$  seconds. At the end of the test, the transistors in the sample lot are required to meet the limits for  $BV_{CB0}$ ,  $BV_{EB0}$ , and  $h_{FE}$  as shown under *Characteristics Endpoint Values*.

**Variable-Frequency Vibration Performance:**

100 to 2000 cps at a Constant Peak Acceleration of 20 g

This test is performed on a sample lot of transistors from each production run. The transistors are rigidly mounted on a vibration platform and subjected to vibration in each of the orientations  $X_1$ ,  $Y_1$ , and  $Z_1$  over a frequency range of 100 to 2000 cycles per second with approximately logarithmic variation of frequency and a constant peak acceleration of 20 g. The entire frequency range from 100 to 2000 cycles per second is covered in not less than four minutes. At the end of the test, the transistors in the sample lot are required to meet the limits for  $BV_{CB0}$ ,  $BV_{EB0}$ , and  $h_{FE}$  as shown under *Characteristics Endpoint Values*.

**Vibration Fatigue:**

Vibrational Acceleration . . . . . 20 max. g

This test is performed on a sample lot of transistors from each production run. The transistors are supplied with the required test voltages while rigidly mounted on a vibration platform. The transistors are then subjected to a simple harmonic motion at any single frequency between 40 and 100 cycles per second with a constant peak acceleration of 20 g. The vibration is applied for 32 hours minimum in each of the orientations  $X_1$ ,  $Y_1$ , and  $Z_1$  (for a total time of 96 hours minimum). At the end of the test, the transistors are required to meet the limits for  $I_{CB0}$  and  $h_{FE}$  as shown under *Characteristics Endpoint Values*.

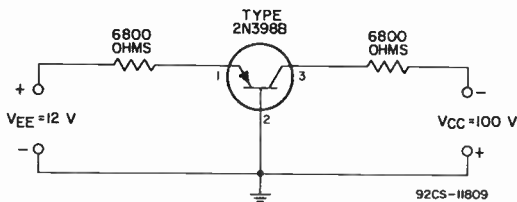
**CHARACTERISTICS ENDPOINT VALUES**

Characteristic	Test Conditions	LIMITS		Units
		Min.	Max.	
$I_{CB0}$	$V_{CB} = -2.5$ volts $I_E = 0$	-	-10	$\mu\text{a}$
$h_{FE}$	$V_{CE} = -0.25$ volt $I_C = -5$ ma	15.5	-	
$BV_{CB0}$	$I_C = -25$ $\mu\text{a}$ $I_E = 0$	-90	-	volts
$BV_{EB0}$	$I_E = -50$ $\mu\text{a}$ $I_C = 0$	-60	-	volts



# 2N398B

## OPERATING-LIFE TEST CIRCUIT



## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the seating plane provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the seals of the leads and damage the transistor.



## Transistor

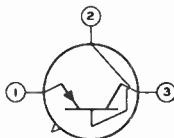
GERMANIUM P-N-P ALLOY-JUNCTION TYPE  
For Computer Switching Applications

### GENERAL DATA

#### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter . . . . .	0.370"
Dimensional Outline . . . . .	JEDEC No. TO-5
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector

### SWITCHING SERVICE

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	-25 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With dc emitter-to-base volts = -1 . . . . .	-24 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-12 max.	volts
COLLECTOR CURRENT . . . . .	-100 max.	ma
EMITTER CURRENT . . . . .	100 max.	ma
TRANSISTOR DISSIPATION: <sup>a</sup>		
At ambient temperature of 25° C or below . . . . .	150 max.	mw
At ambient temperature of 55° C . . . . .	75 max.	mw
At ambient temperature of 71° C . . . . .	35 max.	mw
AMBIENT TEMPERATURE RANGE:		
Operating . . . . .	-65 to +85	°C
Storage . . . . .	-65 to +100	°C
LEAD TEMPERATURE:		
For 10 seconds maximum . . . . .	255 max.	°C

<sup>a</sup> See accompanying *Rating Chart* and also *Transistor-Dissipation Rating Chart* in General Section.

← Indicates a change.



# 2N404

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and at ambient temperature of 25° C unless otherwise specified

Min. Typical Max.

DC Collector Break-down Voltage for dc collector ma. = -0.02, dc emitter ma. = 0 . . . . .	$BV_{CBO}$	-25	-40	-	volts
DC Punch-Through Voltage for dc emitter volts = -1 . . . . .	$V_P$	-24	-40	-	volts
DC Emitter Breakdown Voltage for dc emitter ma. = -0.02, dc collector ma. = 0 . . . . .	$BV_{EBO}$	-12	-35	-	volts
DC Collector-to-Emitter Saturation Voltage:	$V_{CE(sat)}$				
With dc collector ma. = -12, dc base ma. = -0.4 . . . . .		-	-0.1	-0.15	volt
With dc collector ma. = -24, dc base ma. = -1 . . . . .		-	-0.12	-0.2	volt
DC Base-to-Emitter Saturation Voltage:	$V_{BE(sat)}$				
With dc collector ma. = -12, dc base ma. = -0.4 . . . . .		-	-0.25	-0.35	volt
With dc collector ma. = -24, dc base ma. = -1 . . . . .		-	-0.32	-0.4	volt
DC Collector-Cutoff Current for dc collector volts = -12, dc emitter ma. = 0, ambient temperature = 25° C . . . . .	$I_{CBO}$	-	-2	-5	$\mu a$
80° C . . . . .		-	-45	-90	$\mu a$
DC Emitter-Cutoff Current for dc emitter volts = -2.5, dc collector ma. = 0 . . . . .	$I_{EBO}$	-	-1	-	$\mu a$
Collector-to-Base Capacitance for dc collector volts = -6, dc collector ma. = 0 . . . . .	$C_{ob}$	-	12	20	$\mu\mu f$

→ indicates a change.



DC Current Transfer Ratio:	$h_{FE}$				
with dc collector-to-emitter volts = -0.2, dc collector ma. = -24. . . .		24	40	-	
with dc collector-to-emitter volts = -0.15, dc collector ma. = -12. . . .		30	50	-	
Alpha-Cutoff Frequency for dc collector volts = -6, dc collector ma. = -1. . . .	$f_{ab}$	4	13	-	Mc
Stored Base Charge for dc collector ma. = -10, dc base ma. = -1 . . . . .	$Q_S$	-	800	1400	$\mu\text{Coulombs}$
Thermal Time Constant. . . . .	$\tau_1$	-	10	-	msec
Thermal Resistance:					
Junction-to-free air . . . . .	$R_T$	-	-	500	$^{\circ}\text{C/watt}$

### PERFORMANCE TESTS

This transistor type is tested in accordance with Military Specification MIL-S-19500B.

### OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

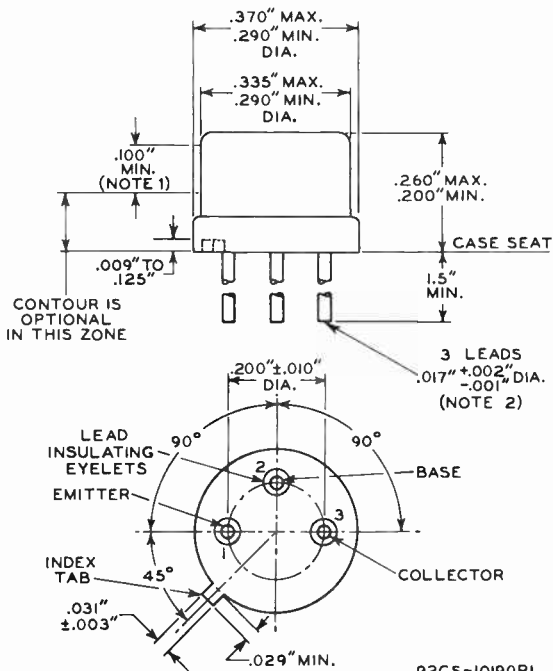
The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the seals of the leads and damage the transistor.

← Indicates a change.



# 2N404

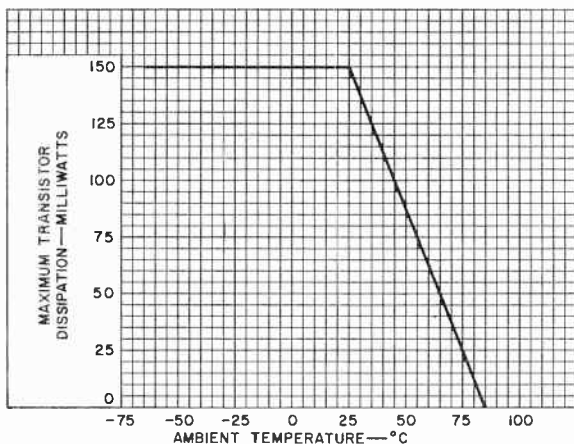
JEDEC No. T0-5



**NOTE 1:** THE DIAMETER IN THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE TOTAL VARIATION IN ACTUAL DIAMETER FROM THE TRUE DIAMETER, DUE TO TAPER AND OUT OF ROUND WITHIN THIS ZONE, WILL NOT EXCEED 0.010".

**NOTE 2:** THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE CASE SEAT. BETWEEN 0.25" AND 1.5", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

## RATING CHART



92CS-10907RI

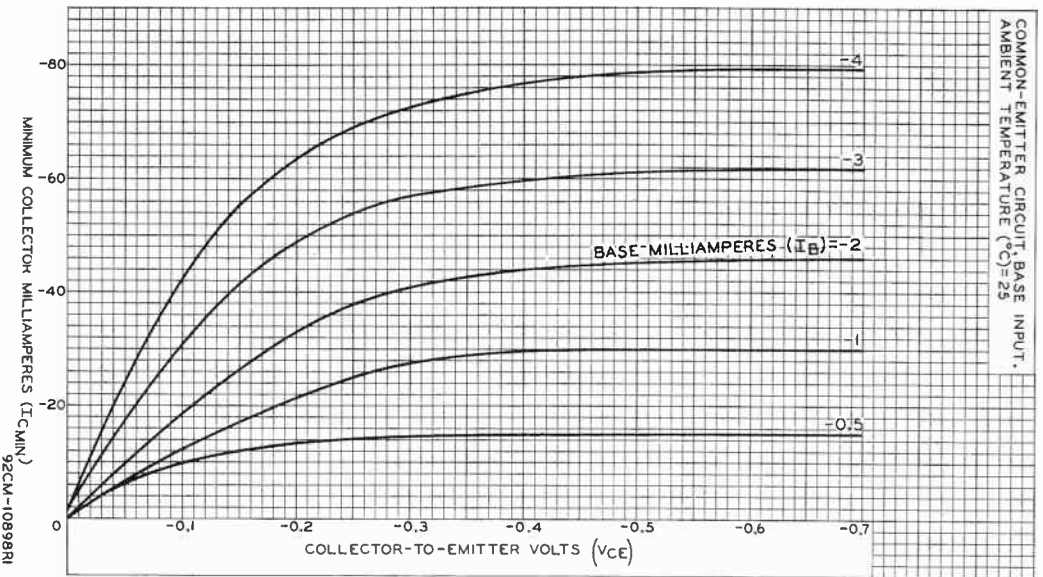
The following curves give the maximum and/or minimum characteristics values for this transistor. These curves were obtained from transistors at the extremes of the characteristics range in a 25-unit sample taken from a large number of production runs.



# 2N404

## MINIMUM COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT,  
AMBIENT TEMPERATURE ( $^{\circ}\text{C}$ ) = 25



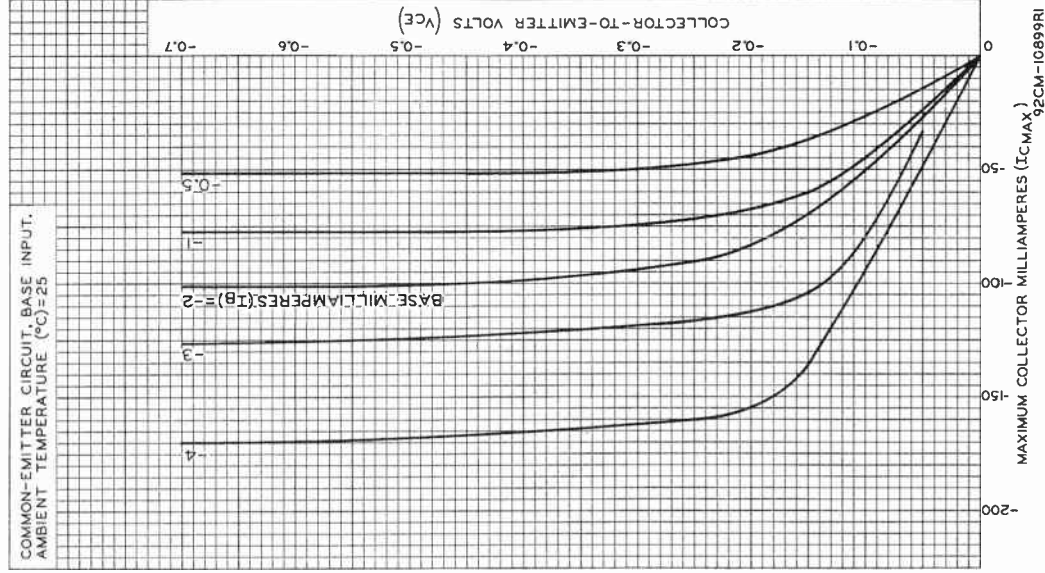
92CM-10898RI

RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division  
Somerville, N. J.



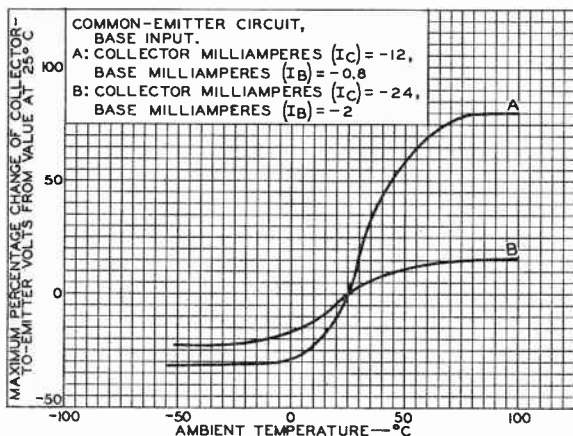
## MAXIMUM COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT,  
 AMBIENT TEMPERATURE ( $^{\circ}\text{C}$ ) = 25

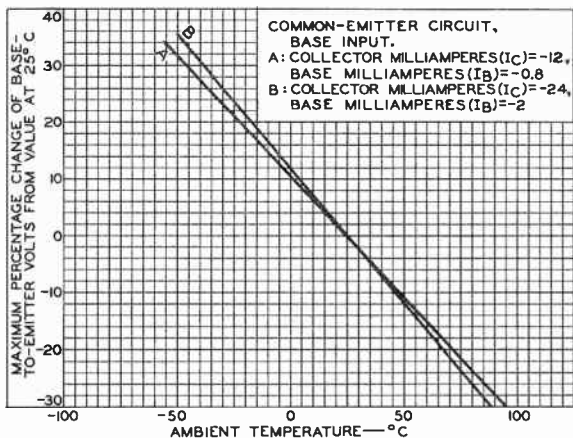


# 2N404

## MAXIMUM CHARACTERISTICS



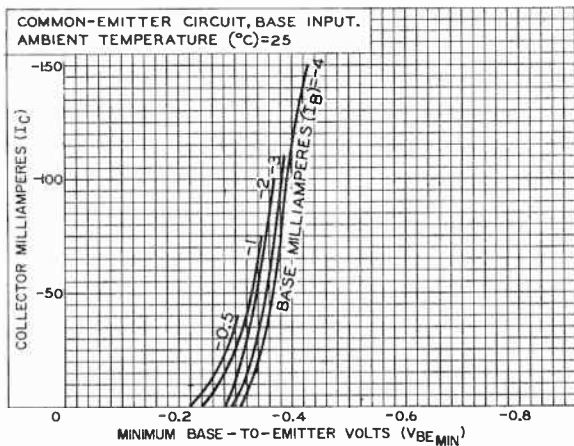
92CS-10895RI



92CS-10889RI

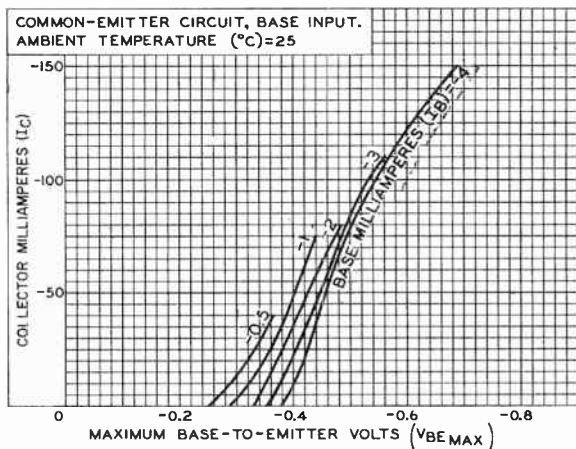


## MINIMUM CHARACTERISTICS



92CS-10888RI

## MAXIMUM CHARACTERISTICS

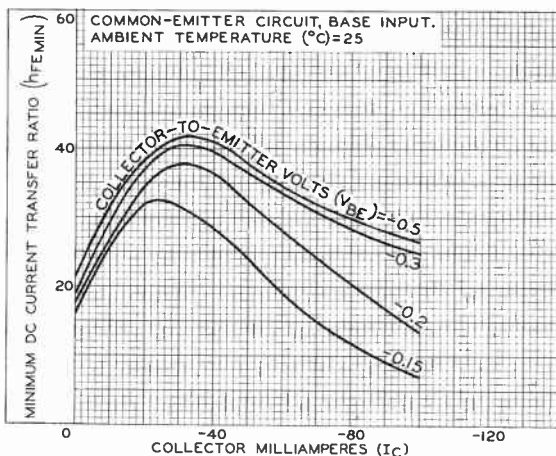


92CS-10887RI



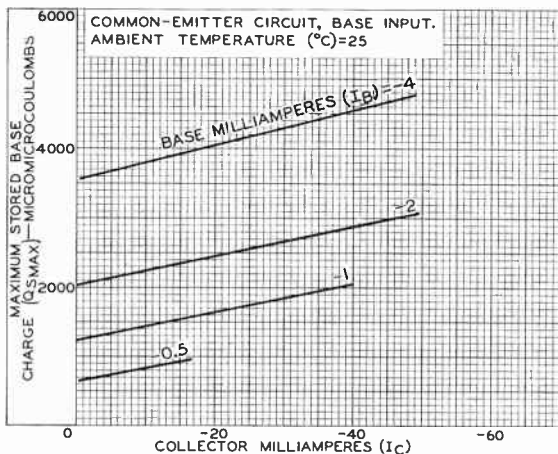
# 2N404

## MINIMUM DC-CURRENT-TRANSFER-RATIO CHARACTERISTICS



92CS-10891R1

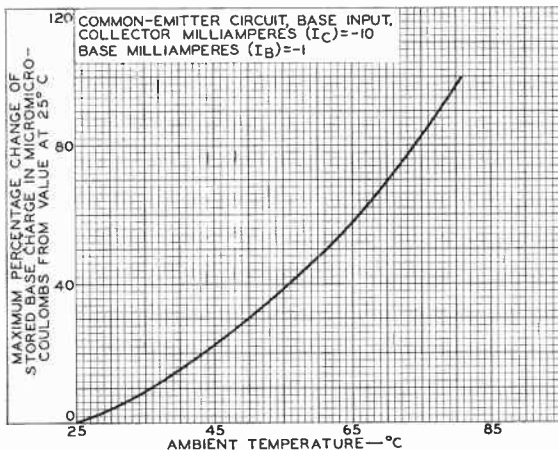
## MAXIMUM STORED-BASE-CHARGE CHARACTERISTICS



92CS-10892R1

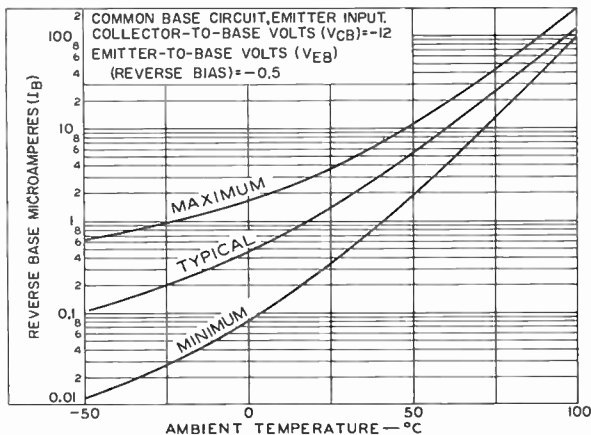


## MAXIMUM CHARACTERISTIC



92CS-10893RI

## REVERSE-BASE-CURRENT CHARACTERISTICS

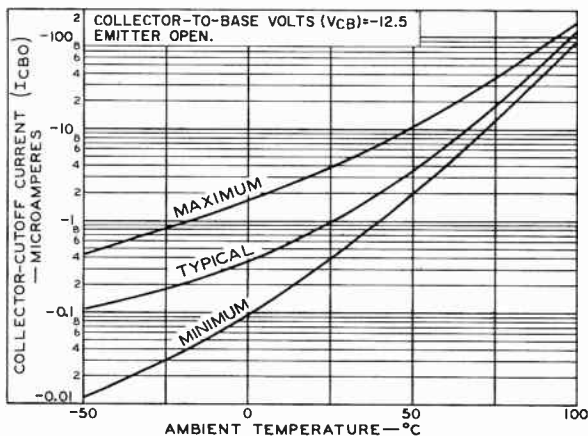


92CS-10884RI



# 2N404

## COLLECTOR-CUTOFF-CURRENT CHARACTERISTICS



92CS-10885R1



# 2N404A

## Transistor

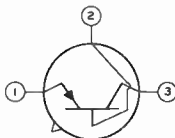
GERMANIUM P-N-P ALLOY-JUNCTION TYPE  
For Computer Switching Applications

### GENERAL DATA

#### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter . . . . .	0.370"
Dimensional Outline . . . . .	JEDEC No. TO-5
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector

### SWITCHING SERVICE

#### Maximum and Minimum Ratings, *Absolute-Maximum Values:*

COLLECTOR-TO-BASE VOLTAGE . . . . .	-40 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE: With dc emitter-to-base volts = -1. . . . .	-35 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-25 max.	volts
COLLECTOR CURRENT . . . . .	-150 max.	ma
EMITTER CURRENT . . . . .	150 max.	ma
TRANSISTOR DISSIPATION: <sup>a</sup>		
At ambient temperature of 25° C . . . . .	150 max.	mw
At ambient temperature of 55° C . . . . .	90 max.	mw
At ambient temperature of 71° C . . . . .	60 max.	mw
AMBIENT-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +100	°C
LEAD TEMPERATURE:		
For immersion in molten solder for 10 seconds maximum. . . . .	255 max.	°C

<sup>a</sup> See accompanying *Rating Chart* and also *Transistor-Dissipation Rating Chart* in General Section.



# 2N404A

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and ambient temperature of 25° C unless otherwise specified

Min. Typical Max.

DC Collector Breakdown Voltage for dc collector ma. = -0.02, dc emitter current = 0.	$BV_{CBO}$	-40	-	-	volts
DC Emitter Breakdown Voltage for dc emitter ma. = -0.02, dc collector current = 0.	$BV_{EBO}$	-25	-	-	volts
DC Punch-Through Voltage for dc emitter volts = -1.	$V_{PT}$	-35	-	-	volts
DC Base-to-Emitter Saturation Voltage: For dc collector ma. = -12, dc base ma. = -0.4.	$V_{BE(sat)}$		-	-0.35	volt
For dc collector ma. = -24, dc base ma. = -1.			-	-0.4	volt
DC Collector-to-Emitter Saturation Voltage: For dc collector ma. = -12, dc base ma. = -0.4.	$V_{CE(sat)}$		-	-0.15	volt
For dc collector ma. = -24, dc base ma. = -1.			-	-0.2	volt
Stored Base Charge (See accompanying Test Circuit)	$Q_S$		-	1400	$\mu\text{coulombs}$
DC Collector-Cutoff Current for dc collector volts = -12, dc emitter current = 0, ambient temperature of:	$I_{CBO}$				
25° C			-	-5	$\mu\text{a}$
80° C			-	-90	$\mu\text{a}$
Alpha-Cutoff Frequency for dc collector volts = -6, dc collector ma. = -1.	$f_{ab}$	4	-	-	Mc
DC Current Transfer Ratio: For dc collector-to-emitter volts = -0.15, dc collector ma. = -12.	$h_{FE}$	30	-	-	
For dc collector-to-emitter volts = -0.2, dc collector ma. = -24.		24	-	-	

Collector-to-Base Capacitance for dc collector volts = -6, dc emitter current = -1, frequency

(Mc) = 2. . . . .  $C_{op}$  - - 20  $\mu\mu f$   
 Thermal Time Constant . .  $\tau_1$  - 10 - msec

Thermal Resistance:

Collector junction to free ambient air. . . .  $R_T$  - - 500  $^{\circ}C/watt$

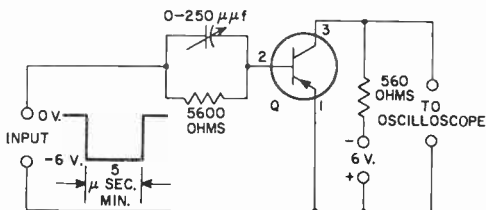
## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.

This transistor is intended for use in single-side printed circuit boards and in conventional wire-in type circuits. If this transistor is used in double-side printed-circuit boards or in printed-circuit boards utilizing eyelets, it may be necessary to use an insulating washer or similar standoff device made of good dielectric material to prevent the solder from shorting the leads to each other or to the board.

## STORED-BASE-CHARGE TEST CIRCUIT



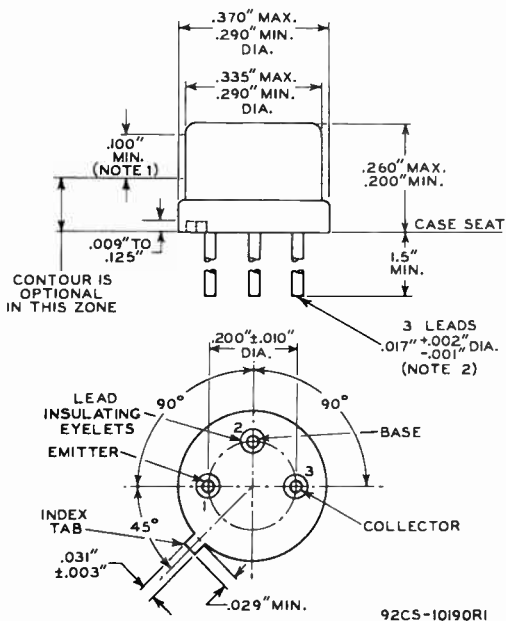
92CS-11042R1

Q: Transistor type 2N404A



# 2N404A

JEDEC No. T0-5

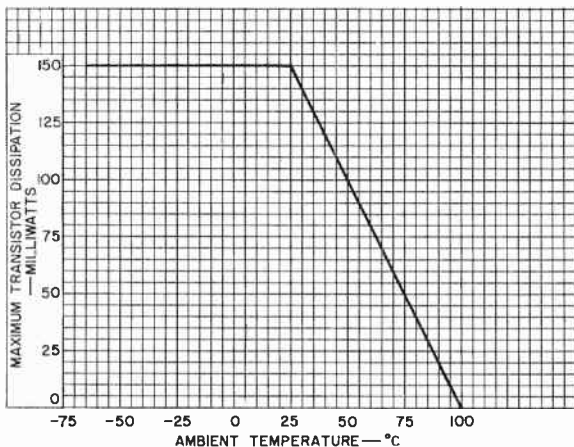


**NOTE 1:** THE DIAMETER IN THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE TOTAL VARIATION IN ACTUAL DIAMETER FROM THE TRUE DIAMETER, DUE TO TAPER AND OUT OF ROUND WITHIN THIS ZONE, WILL NOT EXCEED  $0.010''$ .

**NOTE 2:** THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN  $0.05''$  AND  $0.25''$  FROM THE CASE SEAT. BETWEEN  $0.25''$  AND  $1.5''$ , A MAXIMUM DIAMETER OF  $0.021''$  IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.



## RATING CHART



92CS-11044R1







2N404

2N404

## JUNCTION TRANSISTOR

GERMANIUM F-N-P ALLOY TYPE

For "on-off" control applications

## GENERAL DATA

## Mechanical:

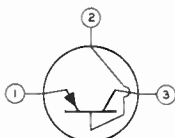
Operating Position. . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.250"
Maximum Diameter. . . . .	0.360"
Case. . . . .	Metal
Envelope Seals. . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length. . . . .	1.5"
Orientation and diameter. . . . .	See Dimensional Outline

## BOTTOM VIEW

Lead 1 - Emitter

Lead 3 - Collector

Lead 2 - Base



## SWITCHING SERVICE

## Maximum Ratings, Absolute Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	-25 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE. . . . .	-24 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-12 max.	volts
COLLECTOR CURRENT . . . . .	-100 max.	ma
EMITTER CURRENT . . . . .	100 max.	ma
COLLECTOR DISSIPATION (See Rating Chart):		
At ambient temperature of 25° C . . . . .	120 max.	mw
At ambient temperature of 55° C . . . . .	35 max.	mw
At ambient temperature of 71° C . . . . .	10 max.	mw
AMBIENT TEMPERATURE (During operation). . . . .	85 max.	°C
STORAGE-TEMPERATURE RANGE . . . . .	-55 to +85	°C

## CHARACTERISTICS RANGE VALUES FOR EQUIPMENT DESIGN

Voltage values are given with respect to the base and ambient temperature = 25° C, unless otherwise specified

	Typical Values	Range Values		
		Min.	Max.	
DC Collector Breakdown Voltage with dc collector current = -20 $\mu$ a, dc emitter current = 0 . . . . .	-40	-25	-	volts
DC Collector Cutoff Current with dc collector voltage = -12 volts, dc emitter current = 0 . . . . .	-2	-	-5	$\mu$ a

4-58

SEMICONDUCTOR DIVISION

TENTATIVE DATA 1

RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY



2N404

## JUNCTION TRANSISTOR

	Typical Values	Range Values		
		Min.	Max.	
DC Collector Cutoff Current with dc collector voltage = -12 volts, dc emitter current = 0, and ambient temperature = 80° C .	-45	-	-90	$\mu$ a
DC Emitter Breakdown Voltage with dc emitter current = -20 $\mu$ a, dc col- lector current = 0 .	-35	-12	-	volts
DC Emitter Cutoff Current with dc emitter voltage = -2.5 volts, dc collector current = 0 . . . . .	-1	-	-2.5	$\mu$ a
DC Collector-to- Emitter (Punch- Through) Voltage* . .	-40	-24	-	volts
DC Collector-to- Emitter Saturation Voltage with dc collector current = -12 ma., dc base current = 0.4 ma. . . . .	-0.10	-	-0.15	volt
DC Base-to-Emitter Saturation Voltage with dc collector current = -12 ma., dc base current = -0.4 ma. . . . .	-0.25	-	-0.35	volt
DC Collector-to- Emitter Saturation Voltage with dc collector current = -24 ma., dc base current = 1 ma. . . . .	-0.12	-	-0.2	volt
DC Base-to-Emitter Saturation Voltage with dc collector current = -24 ma., dc base current = 1 ma. . . . .	-0.32	-	-0.4	volt

\*: See next page.



2N404

2N404

# JUNCTION TRANSISTOR

	Typical Values	Range Values		
		Min.	Max.	
Stored Base Charge with dc collector current = -10 ma., dc base current = 1 ma. . . . .	800	-	1400	$\mu\text{coulombs}$
Alpha-Cutoff Frequency with dc collector voltage = -6 volts, dc emitter current = 1 ma. . . . .	12	4	-	Mc
Collector Capacitance with dc collector voltage = -6 volts, dc emitter current = 0.	12	-	20	$\mu\text{f}$
Junction Temperature Rise (In free air) .	0.28	-	0.35	$^{\circ}\text{C}/\text{mw}$

\* The dc collector-to-emitter (punch-through) voltage may be determined by connecting a high-impedance voltmeter (11 megohms or greater) between the emitter and base and measuring the collector-to-base voltage which causes the emitter to assume an emitter-to-base floating voltage of -1 volt. In making this test, care must be taken not to exceed the maximum collector-to-base voltage rating.

## OPERATING CONSIDERATIONS

The 2N404 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of the 2N404 are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

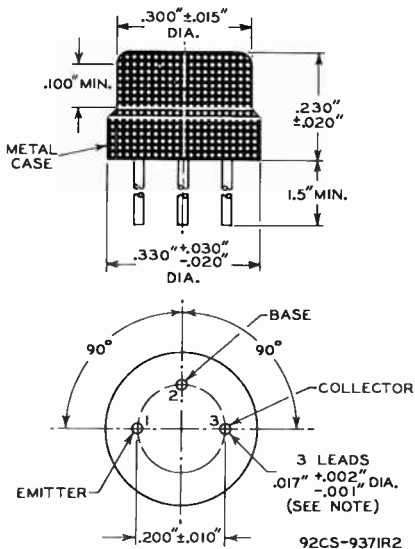
When dip soldering is employed in the assembly of printed circuitry using the 2N404, the temperature of the solder should not exceed  $230^{\circ}\text{C}$  for a maximum immersion period of 10 seconds.

2N404



2N404

## JUNCTION TRANSISTOR



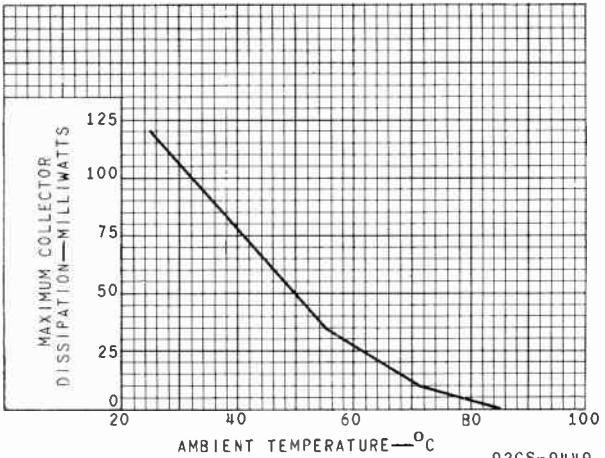
NOTE: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.050" AND 0.250" FROM THE BASE SEAT. BETWEEN 0.250" AND 1.50", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.



2N404

2N404

# COLLECTOR-DISSIPATION RATING CHART



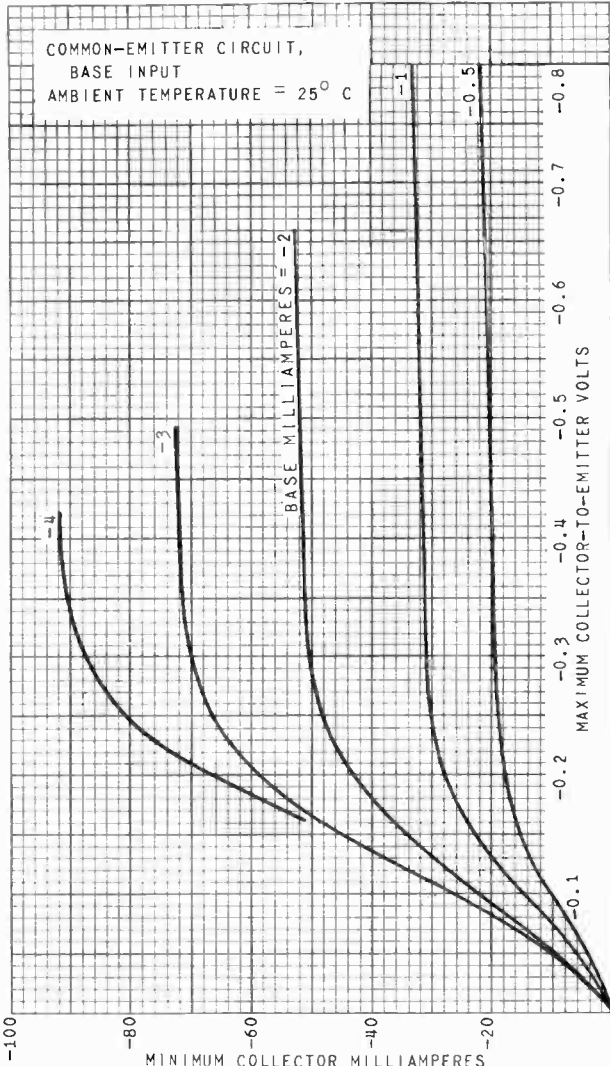
92CS-9449

2N404



2N404

# RANGE OF COLLECTOR CHARACTERISTICS For Switching Applications



MINIMUM COLLECTOR MILLIAMPERES

SEMICONDUCTOR DIVISION

RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

92CS-9451





2N405

# 2N405

## JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

*For audio-frequency driver-amplifier applications*

The 2N405 is the same as the 2N406 except for the following items:

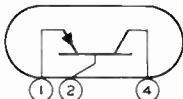
### Mechanical:

Maximum Overall Length . . . . .	0.697"
Maximum Seated Length . . . . .	0.495"
Maximum Diameter . . . . .	0.260"
Base . . . . .	Small-Round Linotetrar 3-Pin (JETEC No.E3-25)

Pin 1 - Emitter

Pin 4 - Collector

Pin 2 - Base



### OPERATING CONSIDERATIONS

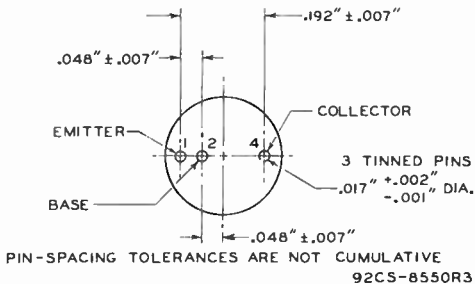
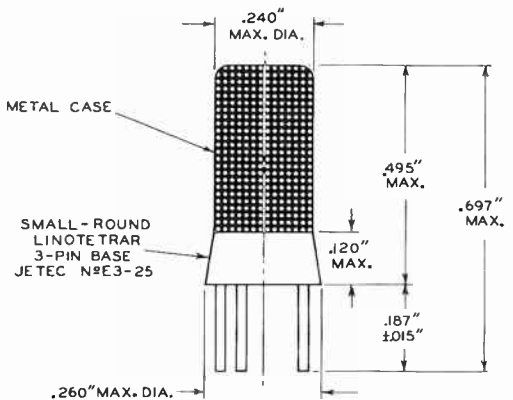
The 2N405 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

2N405



2N405

## JUNCTION TRANSISTOR





2N406

# 2N406

## JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For audio-frequency driver-amplifier applications

### GENERAL DATA

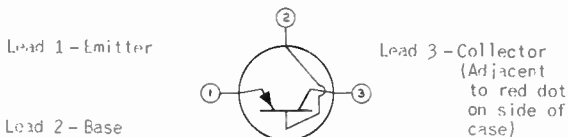
Electrical, At Ambient Temperature of 25° C:

Maximum DC Collector Current for dc collector-to-base voltage of -12 volts with emitter open. . . . .	-14	μA
Maximum DC Emitter Current for dc emitter-to-base voltage of -2.5 volts with collector open . . . . .	-14	μA

### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads). . . . .	0.405"
Maximum Diameter . . . . .	0.240"
Dimensional Outline . . . . .	JETEC No. TO-1
Case . . . . .	Metal
Envelope Seals . . . . .	Hermetic
Leads, Flexible. . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See Dimensional Outline

### BOTTOM VIEW



### AUDIO-FREQUENCY DRIVER-AMPLIFIER — Class A

#### Maximum Ratings, Absolute Values:

COLLECTOR-TO-BASE VOLTAGE (DC + Peak AC) . . . . .	-20 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE (DC + Peak AC). . . . .	-18 max.	volts
EMITTER-TO-BASE VOLTAGE (DC + Peak AC) . . . . .	-2.5 max.	volts
DC COLLECTOR CURRENT . . . . .	-35 max.	mA
DC EMITTER CURRENT . . . . .	35 max.	mA
COLLECTOR DISSIPATION:		
At ambient temperature of 25° C . . . . .	150 max.	mW
At ambient temperature of 55° C . . . . .	50 max.	mW
At ambient temperature of 71° C . . . . .	20 max.	mW
AMBIENT TEMPERATURE (During operation) . . . . .	71 max.	°C
STORAGE-TEMPERATURE RANGE. . . . .	-65 to +85	°C

Characteristics, At Ambient Temperature of 25° C:

Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage. . . . .	-6	volts
DC Emitter Current . . . . .	1	mA



2N406

## JUNCTION TRANSISTOR

## Power Gain:

With load resistance = 8500 ohms,  
and input resistance = 750 ohms . . . . . 43 db

## Small-Signal T Parameters:\*

DC Collector-to-Emitter Voltage ( $V_{CE}$ ) . . . . . -6 volts  
DC Emitter Current ( $I_E$ ) . . . . . 1 ma  
Emitter Resistance ( $r_e$ ) . . . . . 17 ohms  
Base Resistance ( $r_b$ ) . . . . . 500 ohms  
Mutual Resistance ( $r_m$ ) . . . . . 2.04 megohms  
Collector Resistance ( $r_c$ ) . . . . . 2.1 megohms  
Current Transfer Ratio ( $\alpha_f$ )<sup>■</sup> . . . . . -35

Small-Signal Hybrid- $\pi$  Parameters:\*

DC Collector-to-Emitter Voltage ( $V_{CE}$ ) . . . . . -6 volts  
DC Emitter Current ( $I_E$ ) . . . . . 1 ma  
Resistance  $r_{bb}$  . . . . . 120 ohms  
Conductance  $g_{b'e}$  . . . . . 1070  $\mu$ hos  
Conductance  $g_{ce}$  . . . . . 6.5  $\mu$ hos  
Conductance  $g_{b'c}$  . . . . . 0.295  $\mu$ ho  
Capacitance  $C_{b'e}$  . . . . . 9430  $\mu$ f  
Capacitance  $C_{b'c}$  . . . . . 40  $\mu$ f  
Intrinsic Transconductance ( $g_m$ ) . . . . . 37500  $\mu$ hos

## Small-Signal H Parameters:\*

DC Collector-to-Emitter Voltage ( $V_{CE}$ ) . . . . . -6 volts  
DC Emitter Current ( $I_E$ ) . . . . . 1 ma  
Input Resistance, ac output circuit  
shorted ( $h_i$ ) . . . . . 1115 ohms  
Reverse Voltage Transfer Ratio,  
input circuit open ( $h_r$ ) . . . . .  $2.93 \times 10^{-4}$   
Forward Current Transfer Ratio,  
ac output circuit shorted ( $h_f$ ) . . . . . 35  
Output Conductance, input circuit  
open ( $h_o$ ) . . . . . 17.2  $\mu$ hos

*Common-Base Circuit, Emitter Input*

DC Collector-to-Base Voltage . . . . . -6 volts  
DC Emitter Current . . . . . 1 ma  
Frequency at which the current transfer  
ratio drops to 0.707 times its value  
at 1 kc . . . . . 650 Mc

\* As derived from corresponding equivalent circuit shown under type 2N104.

■ Measured at 1 kc.

## OPERATING CONSIDERATIONS

The 2N406 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of the 2N406 are usually soldered to the circuit elements. Soldering of the leads may be made



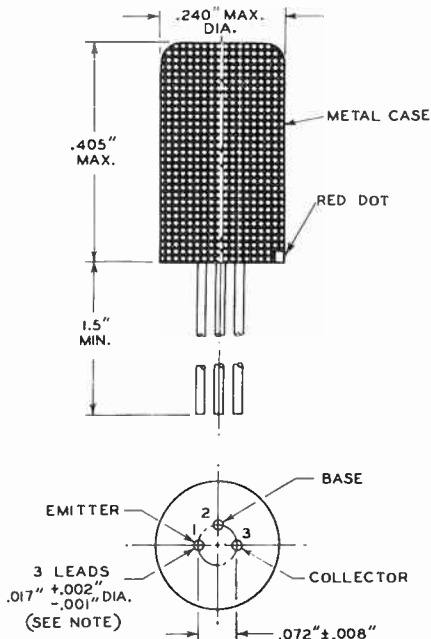
2N406

2N406

# JUNCTION TRANSISTOR

close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using the 2N406, the temperature of the solder should not exceed 230° C for a maximum immersion period of 10 seconds.



92CS-9148R2

NOTE: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.050" AND 0.250" FROM THE BASE SEAT. BETWEEN 0.250" AND 1.50", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

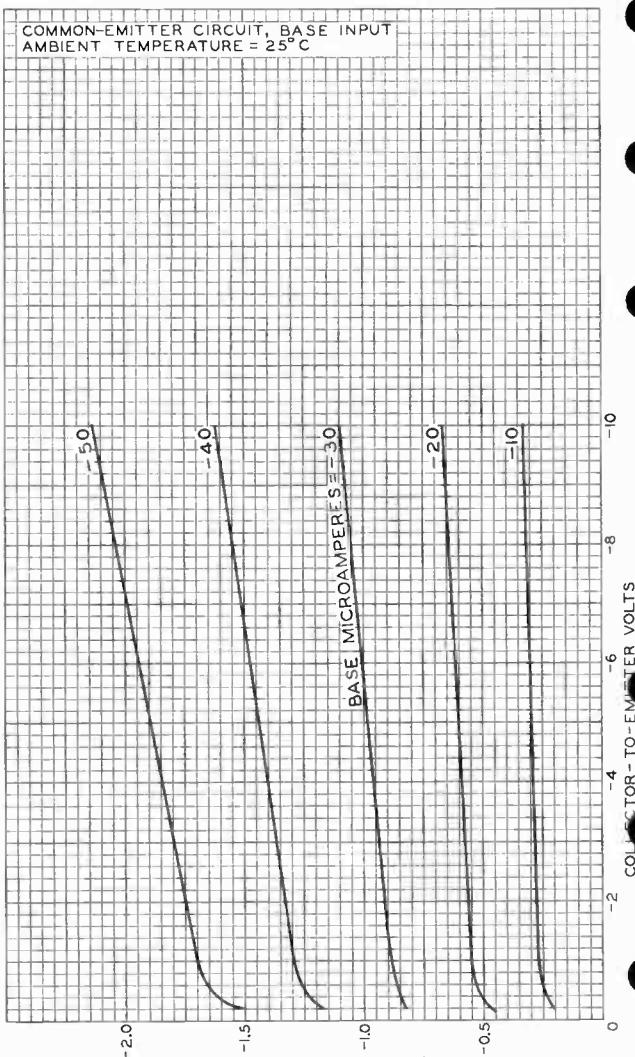
2N406



2N406

### AVERAGE COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE = 25°C



COLLECTOR MILLIAMPERES  
SEMICONDUCTOR DIVISION

RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

92CM-9464RI



2N407

# 2N407

## JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

*For large-signal audio-frequency applications*

The 2N407 is the same as the 2N408 except for the following items:

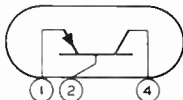
### Mechanical:

Maximum Overall Length . . . . .	0.697"
Maximum Seated Length . . . . .	0.495"
Maximum Diameter . . . . .	0.260"
Base . . . . .	Small-Round Linotetar 3-Pin (JFTEC No. E3-25)

Pin 1 - Emitter

Pin 4 - Collector

Pin 2 - Base



### OPERATING CONSIDERATIONS

The 2N407 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

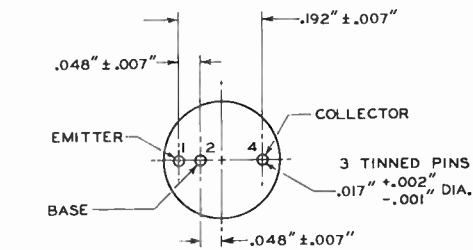
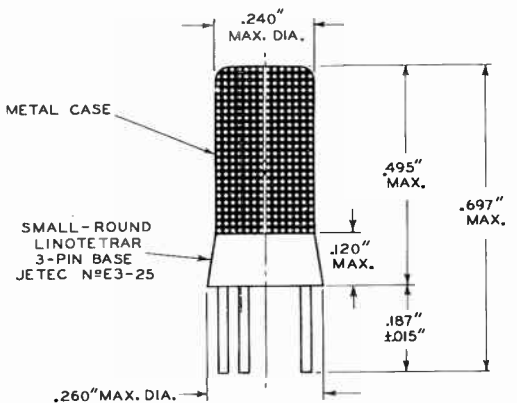
In class B service, when the 2N407 is operated at ambient temperatures other than 25° C, the base-to-emitter voltage should be reduced or increased by approximately 0.002 volt for each degree the ambient temperature is above or below 25° C, respectively. When this transistor is operated under varying ambient temperatures, some form of temperature compensation may be used in the base-to-emitter circuit to hold the operating point constant.

2N407



2N407

# JUNCTION TRANSISTOR



PIN-SPACING TOLERANCES ARE NOT CUMULATIVE  
92CS-8550R3





2N408

2N408

## JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For large-signal audio-frequency applications

## GENERAL DATA

Electrical, At Ambient Temperature of 25° C:

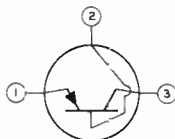
Maximum DC Collector Current for dc collector-to-base voltage of -12 volts with emitter open. . . . .	-14	$\mu\text{A}$
Maximum DC Emitter Current for dc emitter-to-base voltage of -7.5 volts with collector open. . . . .	-14	$\mu\text{A}$

## Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads). . . . .	0.405"
Maximum Diameter . . . . .	0.204"
Dimensional Outline. . . . .	JETEC No. TO-1
Case . . . . .	Metal
Envelope Seals . . . . .	Hermetic
Leads, Flexible. . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See Dimensional Outline

## BOTTOM VIEW

Lead 1 - Emitter

Lead 3 - Collector  
(Adjacent  
to red dot  
on side of  
case)

Lead 2 - Base

## AUDIO-FREQUENCY AMPLIFIER — Class B

Maximum Ratings, Absolute Values:

COLLECTOR-TO-BASE VOLTAGE. . . . .	-20 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE . . . . .	-18 max.	volts
EMITTER-TO-BASE VOLTAGE. . . . .	-2.5 max.	volts
COLLECTOR CURRENT. . . . .	-70 max.	ma
EMITTER CURRENT. . . . .	70 max.	ma
COLLECTOR DISSIPATION:		
At ambient temperature of 25° C . . . . .	150 max.	mW
At ambient temperature of 55° C . . . . .	50 max.	mW
At ambient temperature of 71° C . . . . .	20 max.	mW
AMBIENT TEMPERATURE (During operation) . . . . .	71 max.	°C
STORAGE-TEMPERATURE RANGE. . . . .	-65 to +85	°C

Characteristics, At Ambient Temperature of 25° C:

Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage. . . . .	-1	volt
DC Collector Current . . . . .	-50	ma
Large-Signal DC Current Transfer Ratio . . . . .	65	



2N408

## JUNCTION TRANSISTOR

Typical Push-Pull Operation, At Ambient Temperature of 25° C:

Common-Emitter Circuit, Base Input

Unless otherwise specified, values are for 2 transistors

DC Collector-to-Emitter Supply Voltage. . . . .	-4.5	-9	volts
DC Base-to-Emitter Voltage . .	-0.15	-0.15	volt
Peak Collector Current (Per transistor). . . . .	-35	-40	ma
Zero-Signal DC Collector Current (Per transistor). . . . .	-2	-2	ma
Max.-Signal DC Collector Current (Per transistor). . . . .	-11.5	-13	ma
Signal-Source Impedance (Base to base) . . . . .	1500	1500	ohms
Load Impedance (Collector to collector) . . . . .	400	800	ohms
Signal Frequency . . . . .	1	1	kc
Circuit Efficiency . . . . .	60	69	%
Power Gain . . . . .	30	33	db
Total Harmonic Distortion. . .	10 max.	10 max.	%
Max.-Signal Power Output . . .	75	160	mw

## OPERATING CONSIDERATIONS

The 2N408 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

In class B service, when the 2N408 is operated at ambient temperatures other than 25° C, the base-to-emitter voltage should be reduced or increased by approximately 0.002 volt for each degree the ambient temperature is above or below 25° C, respectively. When this transistor is operated under varying ambient temperatures, some form of temperature compensation may be used in the base-to-emitter circuit to hold the operating point constant.

The flexible leads of the 2N408 are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using the 2N408, the temperature of the solder should not exceed 230° C for a maximum immersion period of 10 seconds.

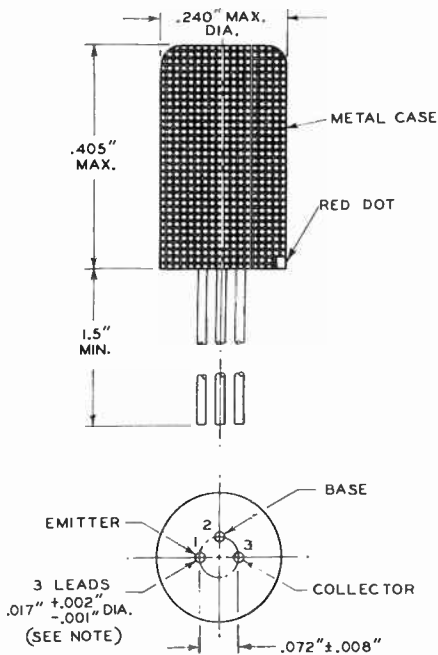
Curves shown under Type 2N109 also apply to the 2N408



2N408

2N408

# JUNCTION TRANSISTOR



92CS-9148R2

NOTE: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.050" AND 0.250" FROM THE BASE SEAT. BETWEEN 0.250" AND 1.50", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.





2N409

2N409

# JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For 455-kc intermediate-frequency applications

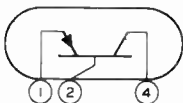
The 2N409 is the same as the 2N410 except for the following items:

### Mechanical:

Maximum Overall Length. . . . .	0.697"
Maximum Seated Length . . . . .	0.495"
Maximum Diameter. . . . .	0.260"
Base. . . . .	Small-Round Linotetrap 3-Pin (JETEC No. E3-25)

Pin 1 - Emitter

Pin 4 - Collector



Pin 2 - Base

### OPERATING CONSIDERATIONS

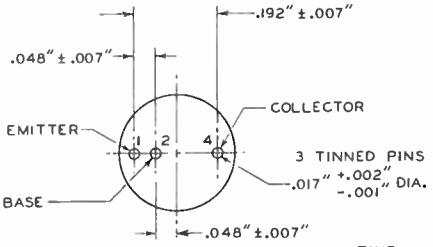
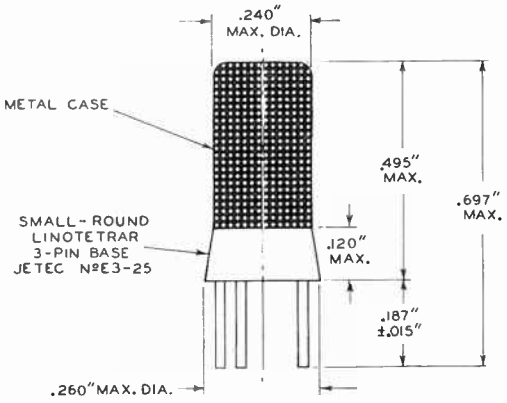
The 2N409 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

2N409



2N409

# JUNCTION TRANSISTOR



PIN-SPACING TOLERANCES ARE NOT CUMULATIVE  
92CS-8550R3



2N410

2N410

## JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For 455-kc intermediate-frequency applications

## GENERAL DATA

Electrical, At Ambient Temperature of 25° C:

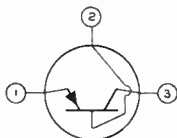
Minimum DC Collector-to-Base Voltage for dc collector current of -10 $\mu$ a with emitter open. . . . .	-13	volts
Maximum DC Collector Current for dc collector-to-base voltage of -13 volts with emitter open. . . . .	-10	$\mu$ a
Maximum DC Emitter Current for dc emitter-to-base voltage of -0.5 volt with collector open. . . . .	-12	$\mu$ a

## Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads). . . . .	0.405"
Maximum Diameter . . . . .	0.240"
Dimensional Outline. . . . .	JETEC No. TO-1
Case . . . . .	Metal
Envelope Seals . . . . .	Hermetic
Leads, Flexible. . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See Dimensional Outline

## BOTTOM VIEW

Lead 1 - Emitter

Lead 3 - Collector  
(Adjacent  
to red dot  
on side of  
case)

Lead 2 - Base

## INTERMEDIATE-FREQUENCY AMPLIFIER

Maximum Ratings, Absolute Values:

DC COLLECTOR-TO-BASE VOLTAGE . . . . .	-13 max.	volts
DC EMITTER-TO-BASE VOLTAGE . . . . .	-0.5 max.	volt
DC COLLECTOR CURRENT . . . . .	-15 max.	ma
DC EMITTER CURRENT . . . . .	15 max.	ma
COLLECTOR DISSIPATION:		
At ambient temperature of 25° C. . . . .	80 max.	mW
At ambient temperature of 55° C. . . . .	35 max.	mW
At ambient temperature of 71° C. . . . .	10 max.	mW
AMBIENT TEMPERATURE (During operation) . . . . .	71 max.	°C
STORAGE-TEMPERATURE RANGE. . . . .	-65 to +85	°C



2N410

## JUNCTION TRANSISTOR

Characteristics, At Ambient Temperature of 25° C:

Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage . . . . .	-9	-9	volts
DC Emitter Current . . . . .	0.5	1	ma
Current Transfer Ratio <sup>■</sup> . . . . .	-45	-48	

Small-Signal Hybrid- $\pi$  Parameters:<sup>\*</sup>

DC Collector-to-Emitter Voltage ( $V_{CE}$ ) . . . . .	-9	-9	volts
DC Emitter Current ( $I_E$ ) . . . . .	0.5	1	ma
Resistance $r_{bb'}$ . . . . .	85	75	ohms
Conductance $g_{b'e}$ . . . . .	425	800	$\mu$ mhos
Conductance $g_{ce}$ . . . . .	4.6	8.6	$\mu$ mhos
Conductance $g_{b'c}$ . . . . .	0.22	0.25	$\mu$ mho
Capacitance $C_{b'e}$ . . . . .	540	1100	$\mu$ mf
Capacitance $C_{b'c}$ . . . . .	9.5	9.5	$\mu$ mf
Intrinsic Transconductance ( $g_m$ ) . . . . .	19300	38600	$\mu$ mhos
Frequency <sup>•</sup> for unity power amplification . . . . .	13	14	Mc

Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage . . . . .	-9	-9	volts
DC Emitter Current . . . . .	0.5	1	ma
Current Transfer Ratio <sup>■</sup> . . . . .	0.978	0.980	
Frequency at which the current transfer ratio drops to 0.707 times its value at 1 kc. . . . .	6.8	6.7	Mc

Typical Operation, At Ambient Temperature of 25° C:

Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage . . . . .	-9	-9	volts
DC Emitter Current . . . . .	0.5	1	ma
Input Resistance . . . . .	1000	500	ohms
Output Resistance . . . . .	70000	30000	ohms
Spot Noise Factor <sup>▲</sup> . . . . .	4.5	4.5	db
Maximum Power Gain <sup>▲</sup> . . . . .	38.8	37.8	db
Useful Power Gain . . . . .	28.4 <sup>§</sup>	30.4 <sup>†</sup>	db

<sup>\*</sup> As derived from corresponding equivalent circuit shown under type 2N104.

<sup>•</sup> This frequency (figure of merit) may be calculated from the equation

$$f = \frac{1}{4\pi} \sqrt{\frac{g_m}{r_{bb'} C_{b'e} C_{b'c}}}$$

<sup>■</sup> Measured at 1 kc.

<sup>▲</sup> Measured in a single-tuned unilateralized circuit matched to the generator and load impedances for maximum transfer of power. Transformer insertion losses not included. (Unilateralization is a special case of neutralization in which the resistive as well as the reactive feedback parameters are balanced out. Unilateralization changes a bilateral network into a unilateral network).

<sup>§</sup> A transformer insertion loss of 10.4 db is included in this figure.

<sup>†</sup> A transformer insertion loss of 6.6 db is included in the figure.





2N410

2N410

## JUNCTION TRANSISTOR

### OPERATING CONSIDERATIONS

The 2N410 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of the 2N410 are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

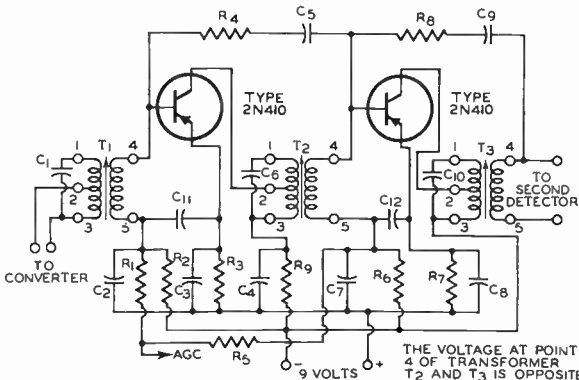
When dip soldering is employed in the assembly of printed circuitry using the 2N410, the temperature of the solder should not exceed 230° C for a maximum immersion period of 10 seconds.

2N410



2N410

## JUNCTION TRANSISTOR

TYPICAL 455-KC INTERMEDIATE-FREQUENCY  
AMPLIFIER CIRCUIT

92CS-9473

THE VOLTAGE AT POINT  
4 OF TRANSFORMER  
T<sub>2</sub> AND T<sub>3</sub> IS OPPOSITE  
IN PHASE TO THAT AT  
POINT 2

NOTE: THE DESIGN OF THIS CIRCUIT PROVIDES STABLE OPERATION AND INTERCHANGEABILITY OF RCA-2N410 TRANSISTORS.

C1 C6 C10: 220  $\mu\mu\text{T}$   
C2: 50  $\mu\text{f}$   
C3 C4 C8: 0.05  $\mu\text{f}$   
C5: 75  $\mu\mu\text{f}$   
C7: 25  $\mu\text{f}$   
C9: 33  $\mu\mu\text{f}$   
C11 C12: 0.1  $\mu\text{f}$   
R1: 12000 ohms

R2: 0.15 megohm  
R3 R7: 820 ohms  
R4: 560 ohms  
R5: 18000 ohms  
R6: 0.1 megohm  
R8: 2000 ohms  
R9: 560 ohms

## Transformer:

	T <sub>1</sub>	T <sub>2</sub>	T <sub>3</sub>
Reflected resistance of primary between terminals 2 and 3 with secondary terminated . . . . .	206000	29000	10900 ohms
Reflected resistance of secondary with primary terminated . . . . .	1000	500	1000 ohms
Turns ratios:			
Terminals 1 and 3 to terminals 2 and 3 . . . . .	1.17	2.48	3.16
Terminals 1 and 3 to terminals 4 and 5 . . . . .	16.8	12.9	10.43
Terminals 2 and 3 to terminals 4 and 5 . . . . .	14.35	7.62	3.3
Core Material . . . . .	Ferrite	Ferrite	Ferrite
Unloaded Q (mounted in chassis) . . . . .	110	61	110
Loaded Q (mounted in chassis) . . . . .	35	35	35

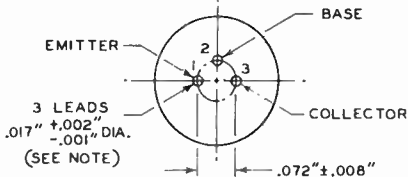
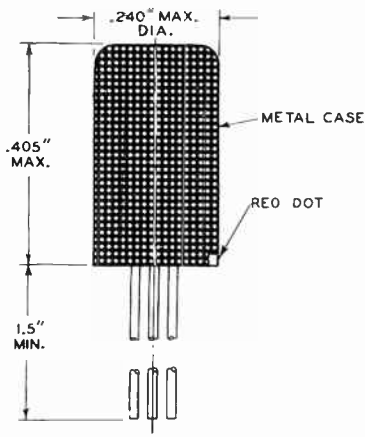
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2N410

2N410

# JUNCTION TRANSISTOR



92CS-9148R2

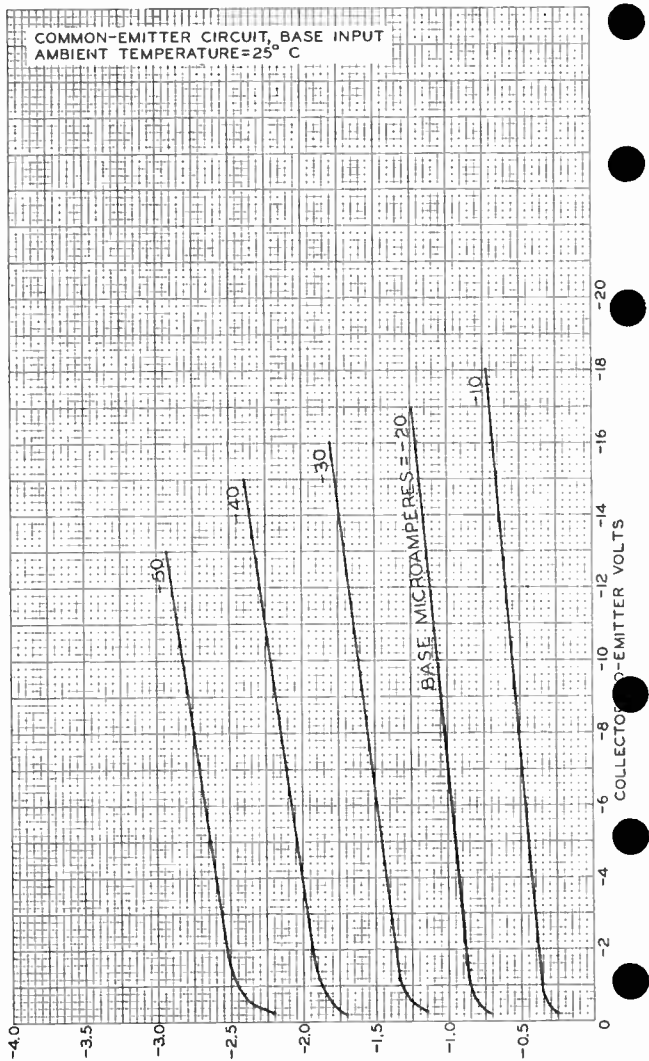
NOTE: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.050" AND 0.250" FROM THE BASE SEAT. BETWEEN 0.250" AND 1.50", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

2N410



2N410

# AVERAGE COLLECTOR CHARACTERISTICS



-4.0

-3.5

-3.0

-2.5

-2.0

-1.5

-1.0

-0.5

0

COLLECTOR MILLIAMPERES

SEMICONDUCTOR DIVISION

RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

92CM-8849RI

-20

-18

-16

-14

-12

-10

-8

-6

-4

-2

0

COLLECTOR-EMITTER VOLTS



2N411

2N411

# JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For 540- to 1600-kc converter applications

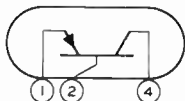
The 2N411 is the same as the 2N412 except for the following items:

### Mechanical:

Maximum Overall Length . . . . .	0.697"
Maximum Seated Length . . . . .	0.495"
Maximum Diameter . . . . .	0.260"
Base . . . . .	Small-Round Linotetrar 3-Pin (JETEC No.E3-25)

Pin 1 - Emitter

Pin 4 - Collector



Pin 2 - Base

### OPERATING CONSIDERATIONS

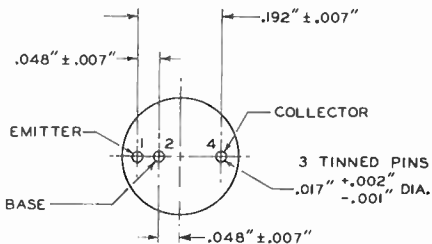
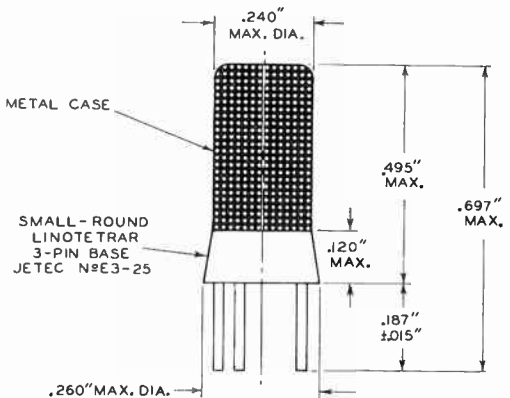
The 2N411 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

2N411



2N411

## JUNCTION TRANSISTOR



PIN-SPACING TOLERANCES ARE NOT CUMULATIVE

92CS-8550R3



2N412

# 2N412

## JUNCTION TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For 540-to 1600-kc converter applications

### GENERAL DATA

Electrical, At Ambient Temperature of 25° C:

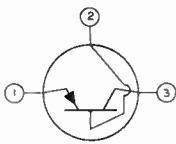
Minimum DC Collector-to-Base Voltage for dc collector current of -10 $\mu$ a with emitter open. . . . .	-13	volts
Maximum DC Collector Current for dc collector-to-base voltage of -13 volts with emitter open . . . . .	-10	$\mu$ a
Maximum DC Emitter Current for dc emitter-to-base voltage of -0.5 volt with collector open . . . . .	-12	$\mu$ a

### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.405"
Maximum Diameter . . . . .	0.240"
Dimensional Outline . . . . .	JETEC No. TO-1
Case . . . . .	Metal
Envelope Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See Dimensional Outline

### BOTTOM VIEW

Lead 1 - Emitter



Lead 3 - Collector  
(Adjacent to red dot on side of case)

Lead 2 - Base

### CONVERTER SERVICE

Maximum Ratings, Absolute Values:

DC COLLECTOR-TO-BASE VOLTAGE . . . . .	-13 max.	volts
DC EMITTER-TO-BASE VOLTAGE . . . . .	-0.5 max.	volt
DC COLLECTOR CURRENT . . . . .	-15 max.	ma
DC EMITTER CURRENT . . . . .	15 max.	ma
COLLECTOR DISSIPATION:		
At ambient temperature of 25° C. . . . .	80 max.	mW
At ambient temperature of 55° C. . . . .	35 max.	mW
At ambient temperature of 71° C. . . . .	10 max.	mW
AMBIENT TEMPERATURE (During operation) . . . . .	71 max.	°C
STORAGE-TEMPERATURE RANGE. . . . .	-65 to +85	°C



2N412

## JUNCTION TRANSISTOR

Characteristics, At Ambient Temperature of 25° C:

Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage. . . . .	-9	volts
DC Emitter Current . . . . .	0.6	ma
Current Transfer Ratio <sup>■</sup> . . . . .	75	

Small-Signal Hybrid- $\pi$  Parameters:<sup>\*</sup>

DC Collector-to-Emitter Voltage ( $V_{CE}$ ). . . . .	-9	volts
DC Emitter Current ( $I_E$ ). . . . .	0.6	ma
Resistance $r_{bb'}$ . . . . .	85	ohms
Conductance $g_{b'e}$ . . . . .	480	$\mu$ hos
Conductance $g_{ce}$ . . . . .	5.4	$\mu$ hos
Conductance $g_{b'c}$ . . . . .	0.23	$\mu$ ho
Capacitance $C_{b'e}$ . . . . .	650	$\mu$ if
Capacitance $C_{b'c}$ . . . . .	9.5	$\mu$ if
Intrinsic Transconductance ( $g_m$ ). . . . .	22600	$\mu$ hos
Frequency <sup>●</sup> for unity power amplification . . . . .	16.5	Mc

Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage . . . . .	-9	volts
DC Emitter Current . . . . .	0.6	ma
Current Transfer Ratio <sup>■</sup> . . . . .	0.987	
Frequency at which the current transfer ratio drops to 0.707 times its value at 1 kc. . . . .	10	Mc

Typical Operation, At Ambient Temperature of 25° C:

Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage. . . . .	-9	volts
DC Emitter Current . . . . .	0.6	ma
Input Resistance . . . . .	700	ohms
Output Resistance. . . . .	75000	ohms
RMS Base-to-Emitter Oscillator Injection Voltage. . . . .	100	mv
Signal Frequency . . . . .	1	Mc
Useful Conversion Power Gain . . . . .	32	db

■ Measured at 1 kc.

\* As derived from corresponding equivalent circuit shown under type 2N104.

● This frequency (figure of merit) may be calculated from the equation

$$f = \frac{1}{4\pi} \sqrt{\frac{g_m}{r_{bb'} C_{b'c} C_{b'e}}}$$

## OPERATING CONSIDERATIONS

The 2N412 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The flexible leads of the 2N412 are usually soldered to the circuit elements. Soldering of the leads may be made





# 2N412

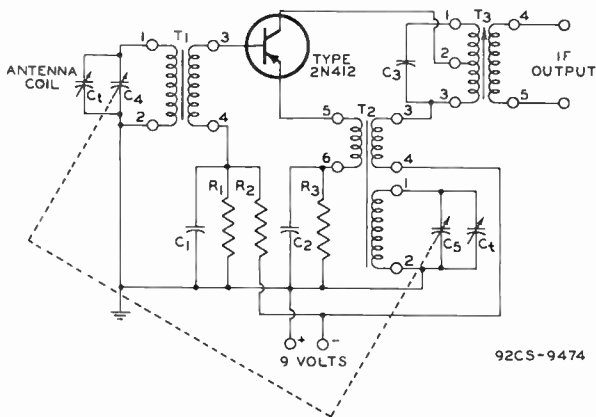
## JUNCTION TRANSISTOR

2N412

close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using the 2N412, the temperature of the solder should not exceed 230° C for a maximum immersion period of 10 seconds.

### TYPICAL SELF-EXCITED CONVERTER CIRCUIT



- |                                  |   |
|----------------------------------|---|
| C1: 0.05 $\mu$ f                 | C <sub>t</sub> : 2 to 20 $\mu$ f (variable) |
| C2: 0.04 $\mu$ f                 | R1: 6800 ohms                               |
| C3: 220 $\mu$ f                  | R2: 18000 ohms                              |
| C4: 12 to 230 $\mu$ f (variable) | R3: 3900 ohms                               |
| C5: 10 to 105 $\mu$ f (variable) |   |

T1: RF Transformer; low-loss ferrite core; unloaded Q (mounted in chassis), 212 at 1 Mc. Primary: 75 turns of 7/41 Litz wire space wound (spacing equal to diameter of wire) in single layer and centered on core; reflected resistance with secondary terminated, 0.3 megohm; inductance (approx.), 353 microhenries. Secondary: 4.5 turns of No. 34 SSE wire wound on ground end of core.

T2: Oscillator Transformer; low-loss ferrite core; unloaded Q (mounted in chassis), 100 at 1455 kc. Primary: 133 turns of 7/41 Litz wire between terminals 1 and 2; inductance (approx.); 207 microhenries. Secondary: 10 turns of No. 34 SSE wire between terminals 3 and 4; 4 turns of No. 34 SSE wire between terminals 5 and 6.

T3: See next page.

2N412

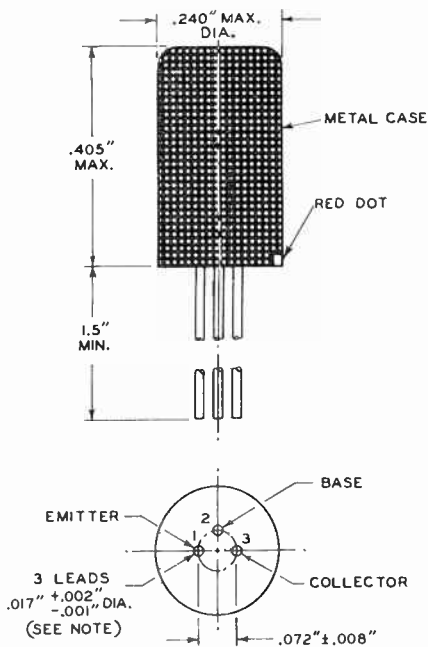


2N412

## JUNCTION TRANSISTOR

T<sub>3</sub>: 1F Transformer; ferrite core; unloaded Q (mounted in chassis), 110 at 455 kc; loaded Q (mounted in chassis), 35 at 455 kc. Turns ratios: terminals 1 and 3 to terminals 2 and 3, 1.17; terminals 2 and 3 to terminals 4 and 5, 14.35; terminals 1 and 3 to terminals 4 and 5, 16.8. Primary: reflected resistance with secondary terminated, 0.206 megohm. Secondary: reflected resistance with primary terminated, 1000 ohms.

Devices and arrangements shown or described herein may use patents of RCA or others. Information contained herein is furnished without responsibility by RCA for its use and without prejudice to RCA's patent rights.



92CS-9148R2

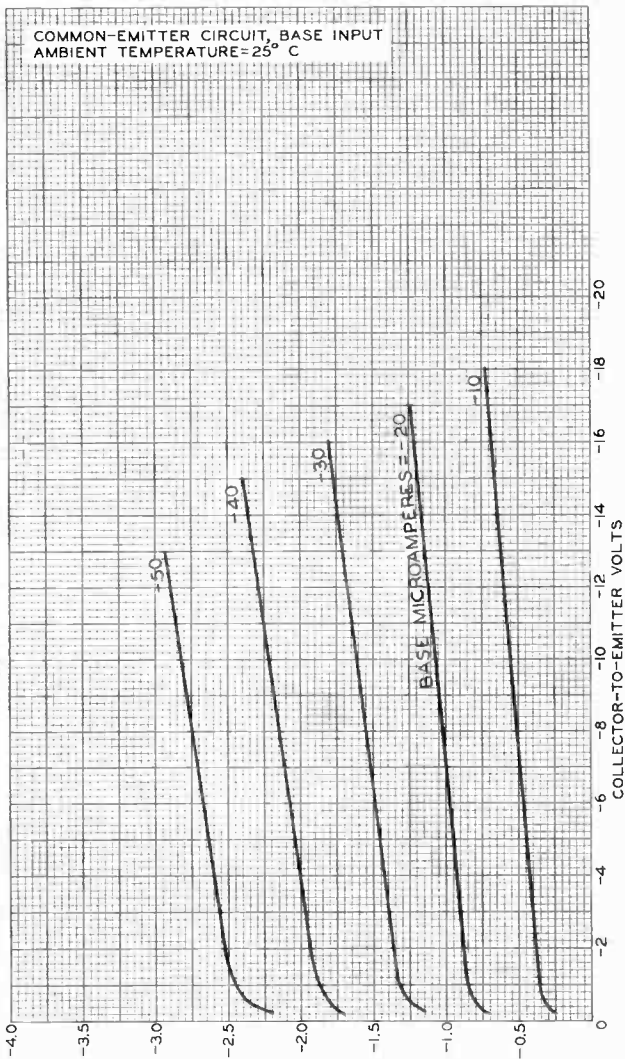
NOTE: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.050" AND 0.250" FROM THE BASE SEAT. BETWEEN 0.250" AND 1.50", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.



2N412

2N412

AVERAGE COLLECTOR CHARACTERISTICS



COLLECTOR MILLIAMPERES

SEMICONDUCTOR DIVISION

RADIO CORPORATION OF AMERICA, SOMERVILLE, NEW JERSEY

92CM-8849RI



## Junction Transistor

## GERMANIUM P-N-P ALLOY TYPE

For Medium-Speed Switching Service in Commercial and Military Data-Processing Systems

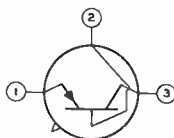
## GENERAL DATA

## Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter . . . . .	0.370"
Dimensional Outline . . . . .	JFDC No. TC-5
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See Dimensional Outline
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base



Lead 3 - Collector

## SWITCHING SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values:*

COLLECTOR-TO-BASE VOLTAGE . . . . .	-30 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-20 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
Base-to-emitter volts = 1 . . . . .	-20 max.	volts
Base open . . . . .	-15 max.	volts
PEAK COLLECTOR CURRENT . . . . .	-400 max.	ma
DC COLLECTOR CURRENT . . . . .	-200 max.	ma
TRANSISTOR DISSIPATION: <sup>a</sup>		
At ambient temperature of 25° C . . . . .	150 max.	mw
At ambient temperature of 55° C . . . . .	75 max.	mw
AMBIENT-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +85	°C
LEAD TEMPERATURE:		
For immersion in molten solder for 10 seconds maximum . . . . .	240 max.	°C

<sup>a</sup> See accompanying Rating Chart.



# 2N414

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to the base unless otherwise specified. Ambient temperature of 25° C.

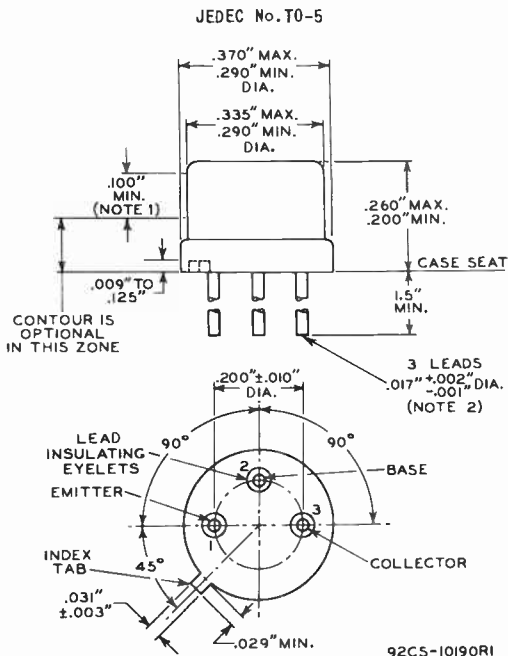
	Min.	Typical	Max.		
DC Collector-Cutoff Current for dc collector volts = -12, emitter open. . . . .	$I_{CBO}$	-	-2	-5	$\mu\text{a}$
DC Emitter-Cutoff Current for dc emitter volts = -12, collector open. . . . .	$I_{EBO}$	-	-2	-5	$\mu\text{a}$
Small-Signal Current Transfer Ratio for dc collector-to-emitter volts = -6, dc emitter ma. = 1, frequency of 1 kc. . . . .	$h_{fe}$	-	80	-	
Small-Signal Open-Circuit Reverse-Voltage Transfer Ratio for dc collector volts = -6, dc emitter ma. = 1, frequency of 1 kc. . . . .	$h_{rb}$	-	$0.5 \times 10^{-3}$	-	
Alpha-Cutoff Frequency for dc collector volts = -6, dc emitter ma. = 1. . . . .	$f_{\alpha b}$	-	8	-	Mc
Small-Signal Short-Circuit Input Impedance for dc collector volts = -6, dc emitter ma. = 1, frequen- cy of 1 kc. . . . .	$h_{ib}$	-	30	-	ohms
Extrinsic Base Resistance for dc collector-to- emitter volts = -6, dc emitter ma. = 1, fre- quency of 6 Mc. . . . .	$r_{bb'}$	-	120	-	ohms
Collector-to-Base Capacitance for dc collector volts = -6, dc emitter ma. = 1. . . . .	$C_{ob}$	-	11	-	$\mu\mu\text{f}$
Power Gain for dc collector- to-emitter volts = -6, dc emitter ma. = 1, frequen- cy of 1.5 Mc. . . . .	PG	-	16	-	db
Noise Factor for dc collec- tor-to-emitter voltage = -6, dc emitter ma. = 1, frequency of 1.5 Mc. . . . .	NF	-	6	-	db

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.



The flexible leads of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.



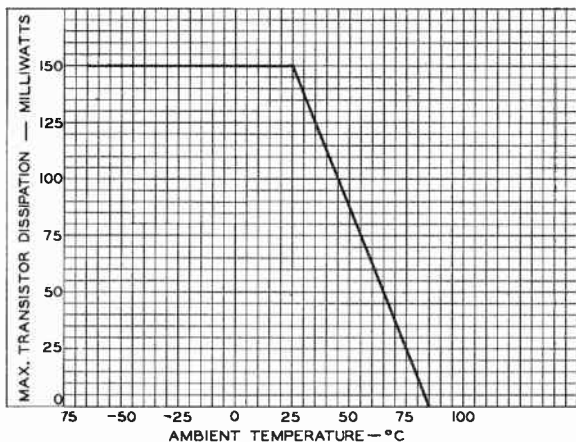
NOTE 1: THE DIAMETER IN THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE TOTAL VARIATION IN ACTUAL DIAMETER FROM THE TRUE DIAMETER, DUE TO TAPER AND OUT OF ROUND WITHIN THIS ZONE, WILL NOT EXCEED  $0.010''$ .

NOTE 2: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN  $0.05''$  AND  $0.25''$  FROM THE CASE SEAT. BETWEEN  $0.25''$  AND  $1.5''$ , A MAXIMUM DIAMETER OF  $0.021''$  IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.



# 2N414

## RATING CHART



92CS-10232R1





## Power Transistor

## GERMANIUM P-N-P ALLOY TYPE

For Power Switching and Amplifier Service  
in Industrial and Military Applications

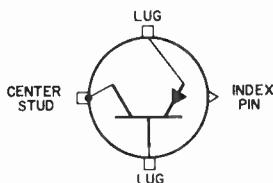
## GENERAL DATA

## Mechanical:

Operating Position . . . . .	Any
Maximum Seated Length . . . . .	0.520"
Maximum Diameter . . . . .	1.250"
Dimensional Outline . . . . .	JEDEC No. TO-36
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic

Terminal Diagram (See *Dimensional Outline*):

BOTTOM VIEW



## INDUSTRIAL SERVICE

*Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and audio-amplifier, relay- and solenoid-actuating circuits*

## Maximum and Minimum Ratings, Absolute-Maximum Values:

## COLLECTOR-TO-BASE VOLTAGE:

With emitter-to-base reverse biased

(DC emitter-to-base volts = -1.5) . . . . .	-40 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-20 max.	volts
COLLECTOR CURRENT . . . . .	-15 max.	amp
EMITTER CURRENT . . . . .	15 max.	amp
BASE CURRENT . . . . .	-4 max.	amp
TRANSISTOR DISSIPATION: <sup>a</sup>		
At case temperatures <sup>b</sup> of 25° C or below.	150 max.	watts
CASE-TEMPERATURE <sup>b</sup> RANGE:		
Operating and storage . . . . .	-65 to +100	°C

## Typical Operation:

*In a common-emitter, base-input, power-switching circuit at case temperature<sup>b</sup> of 25° C*

DC Supply Voltage . . . . .	-12	volts
DC Base-Bias Voltage . . . . .	6	volts
"Or" DC Collector Current . . . . .	-12	amp
"Turn-On" Base Current . . . . .	-2	amp
"Turn-Off" Base Current . . . . .	0	amp

← Indicates a change.



# 2N441

## Switching Time:

Rise time . . . . .	15	$\mu$ sec
Fall time . . . . .	15	$\mu$ sec

<sup>a</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

<sup>b</sup> Measured at any point on seating surface.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and at case temperature<sup>b</sup> of 25° C unless otherwise specified

Min. Typical Max.

### DC Collector-to-Emitter

#### Breakdown Voltage:

With base connected to emitter, dc collector amperes

= -0.3 . . . . .  $BV_{CES}$  -40 - - volts

With base open:

For dc collector amperes = -0.3 . . .  $BV_{CEO}$  - -40 - volts

For dc collector amperes = -1<sup>c</sup> . . . -25 - - volts

### DC Base-to-Emitter Voltage

for dc collector-to-emitter volts = -2, dc collector amperes = -5. . .  $V_{BE}$  - -0.65 - volt

### DC Collector-to-Emitter

#### Saturation Voltage

for dc collector amperes = -12, dc base amperes = -2.  $V_{CE}$  (sat) - -0.3 - volt

### DC Emitter Voltage for dc

collector volts = -40, dc emitter current = 0. . .  $V_{EB}$  - - -1 volt

### DC Punch-Through Voltage.

$V_{PT}$  -40 - - volts

### DC Emitter-Cutoff Current

for dc emitter volts = -20, dc collector current = 0 . . . . .  $I_{EBO}$  - -1 -4 ma

### DC Collector-Cutoff Current:

With dc collector volts = -2, dc emitter current = 0 . . . . .  $I_{CBO}$  - -100 -  $\mu$ a

With dc collector volts = -40, dc emitter current = 0 . . . . . - -2 -4 ma

With dc collector volts = -40, dc emitter current = 0, case temperature<sup>b</sup> = 71° C . . . - - -15 ma

→ Indicates a change.



DC Current Transfer Ratio for dc collector-to- emitter volts = -2, dc collector amperes =	$h_{FE}$			
-5 . . . . .		20	-	40
-12 . . . . .		-	20	-
Beta-Cutoff Frequency for dc collector-to- emitter volts = -6, dc collector amperes = -5 . . . . .	$f_{ae}$	-	10	-
Thermal Resistance: Junction-to-case . . . . .	$R_T$	-	0.35	0.5 °C/watt
Thermal Capacity for pulse duration of 1 to 10 milliseconds . . . . .		-	0.075	-
				watt- sec/°C
Thermal Time Constant . . .	$\tau_1$	-	26.25	-
				msec

<sup>b</sup> Measured at any point on seating surface.

<sup>c</sup> Tested by sweep method to prevent excessive heating of collector junction.

## PERFORMANCE TESTS

This transistor type is designed to pass the environmental tests specified in Military Specification MIL-S-19500B.

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

Electrical connection can be made to the base and emitter lugs by means of clips or by soldering directly to the lugs. When soldering connections are made to the lugs, care should be taken to conduct excessive heat away from the lug seals, otherwise the heat of the soldering operation will crack the glass seals of the lugs and damage the transistor.

This transistor is provided with a single-ended stud for mounting to a heat sink and for electrical connection to the collector. (See accompanying *Suggested Mounting Arrangement*). Electrical connection to the base and to the emitter is made to their respective lugs.

It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.

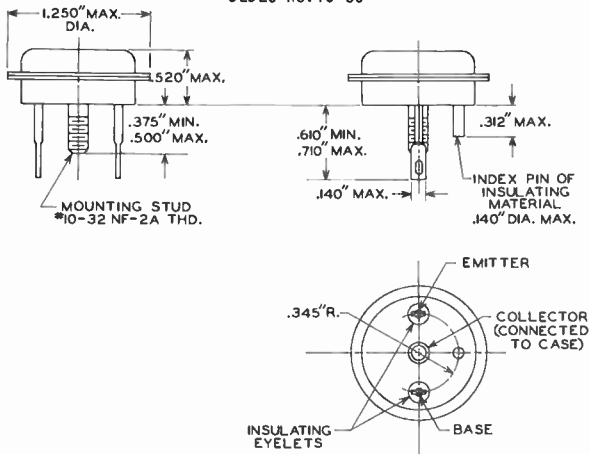
The maximum torque on mounting stud should not exceed 12 inch-pounds.

← Indicates a change.



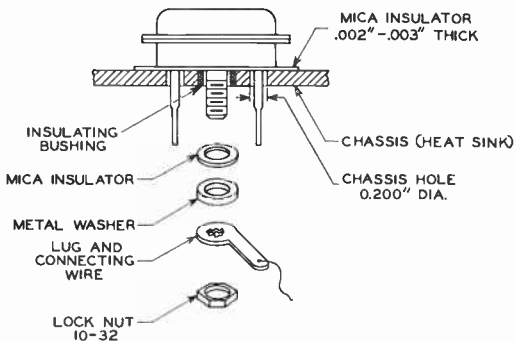
# 2N441

JEDEC No. TO-36



92CM-10612RI

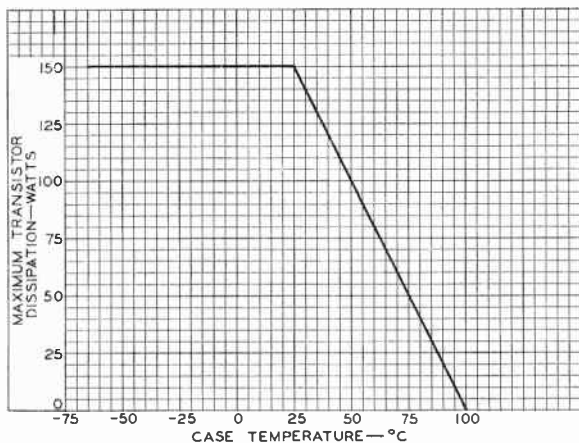
## SUGGESTED MOUNTING ARRANGEMENT



92CS-10624RI

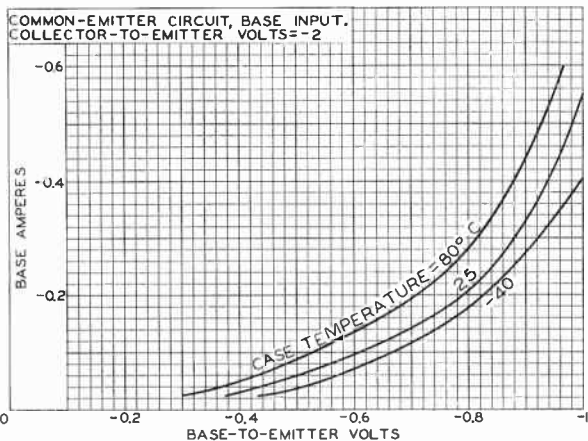


## RATING CHART



92CS-10702R1

## TYPICAL BASE CHARACTERISTICS

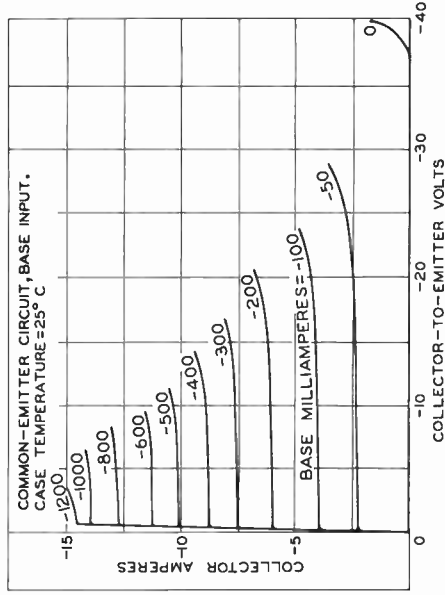


92CS-10717



# 2N441

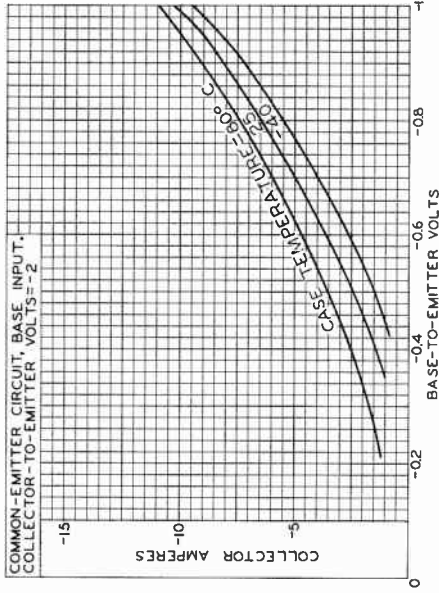
## TYPICAL COLLECTOR CHARACTERISTICS



92CS-10732

World Precision

## TYPICAL CHARACTERISTICS



92CS-10720

## Power Transistor

## GERMANIUM P-N-P ALLOY TYPE

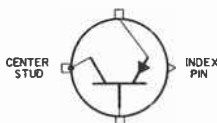
For Power Switching and Amplifier Service  
in Industrial and Military Applications

## GENERAL DATA

## Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	1.230"
Maximum Seated Length. . . . .	0.520"
Maximum Diameter. . . . .	1.250"
Dimensional Outline. . . . .	JEDEC No. TO-36
Case. . . . .	Welded, Metal
Seals. . . . .	Hermetic
Terminal Diagram (See <i>Dimensional Outline</i> ):	

## BOTTOM VIEW



## INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter, chopper,  
voltage- and current-regulator, dc- and audio  
amplifier, relay- and solenoid-actuating circuits

## Maximum and Minimum Ratings, Absolute-Maximum Values:

## COLLECTOR-TO-BASE VOLTAGE:

With emitter-to-base reverse biased

( $\theta_C$ emitter-to-base volts = -1.5) . . . . .	-40 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-20 max.	volts
COLLECTOR CURRENT . . . . .	-15 max.	amp
EMITTER CURRENT . . . . .	15 max.	amp
BASE CURRENT. . . . .	-4 max.	amp

## TRANSISTOR DISSIPATION:

At case temperature of 25° C. . . . . 70 max. watts

## CASE-TEMPERATURE RANGE:

Continuous operation. . . . .	-65 to +95	°C
Intermittent operation. . . . .	-65 to +100	°C
Storage . . . . .	-65 to +100	°C

## Typical Operation:

In a common-emitter, base-input, power-  
switching circuit at case temperature of 25° C

DC Supply Voltage . . . . .	-12	volts
DC Base-Bias Voltage. . . . .	6	volts
"On" DC Collector Current . . . . .	-12	amp
"Turn-On" Base Current. . . . .	-2	amp
"Turn-Off" Base Current . . . . .	0	amp



# 2N441

## Switching Time:

Rise time . . . . .	15	$\mu\text{sec}$
Fall time . . . . .	15	$\mu\text{sec}$

▲ See accompanying *Rating Chart* and also *Transistor-Dissipation Rating Chart* in *General Section*.

## ELECTRICAL CHARACTERISTICS

*Voltage values are given with respect to base and case temperature of 25° C unless otherwise specified*

*Min. Typical Max.*

DC Collector-to-Emitter Breakdown Voltage:						
With base connected to emitter, dc collector amperes = -0.3 . . . . .						
	$BV_{CES}$	-40	-	-	volts	
With base open:						
For dc collector amperes = -0.3 . . . . .						
	$BV_{CEO}$	-	-40	-	volts	
For dc collector amperes = -1 . . . . .						
		-25	-	-	volts	
DC Base-to-Emitter Voltage*						
for dc collector-to-emitter volts = -2, dc collector amperes = -5 . . . . .						
	$V_{BE}$	-	-0.65	-	volt	
DC Collector-to-Emitter Saturation Voltage*						
for dc collector amperes = -12, base amperes = -2 . . . . .						
	$V_{CE}$	-	-0.3	-	volt	
DC Emitter Voltage for dc collector volts = -40, dc emitter amperes = 0 . . . . .						
	$V_{EB}$	-	-	-1	volt	
DC Punch-Through Voltage . . . . .						
	$V_P$	-40	-	-	volts	
DC Emitter-Cutoff Current for dc emitter volts = -20, dc collector amperes = 0 . . . . .						
	$I_{EBO}$	-	-1	-8	ma	
DC Collector-Cutoff Current: $I_{CBO}$						
With dc collector volts = -2, dc emitter amperes = 0 . . . . .						
		-	-100	-	$\mu\text{a}$	
With dc collector volts = -40, dc emitter amperes = 0 . . . . .						
		-	-2	-8	ma	
With dc collector volts = -40, dc emitter amperes = 0, case temperature = 71° C . . . . .						
		-	-	-15	ma	





DC Current Transfer Ratio* $h_{FE}$				
for dc collector-to-emitter volts = -2, dc collector amperes =				
-5 . . . . .	20	-	40	
-12 . . . . .	-	20	-	
Beta-Cutoff Frequency*				
for dc collector-to-emitter volts = -6, dc collector amperes =				
-5 . . . . .	$f_{ae}$	-	10	kc
Thermal Resistance:				
Junction-to-case . . . . .	$R_T$	-	0.7	1 °C/watt
Thermal Capacity for pulse duration of 1 to 10 milliseconds . . . . .		-	0.075	watt-sec/°C
Thermal Time Constant . . . . .	$\tau_1$	-	52.5	msec

• Sweep voltage used to perform test.

\* Measured in a common-emitter, base-input circuit.

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

Electrical connection can be made to the base and emitter terminals by means of clips or by soldering directly to the terminals. When soldering connections are made to the terminals, care should be taken to conduct excessive heat away from the terminal seals, otherwise the heat of the soldering operation will crack the glass seals of the terminals and damage the transistor.

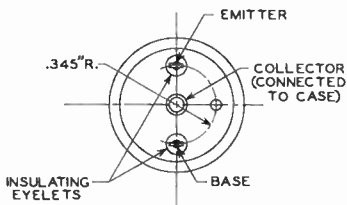
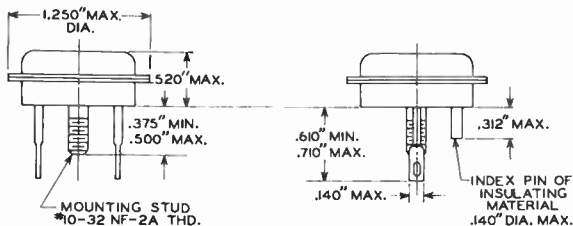
This transistor is provided with a single-ended stud for mounting to a heat sink and for electrical connection to the collector. (See accompanying *Suggested Mounting Arrangement*). Electrical connection to the base and to the emitter is made to their respective terminals.

It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.

The maximum torque on mounting stud should not exceed 12 inch-pounds.

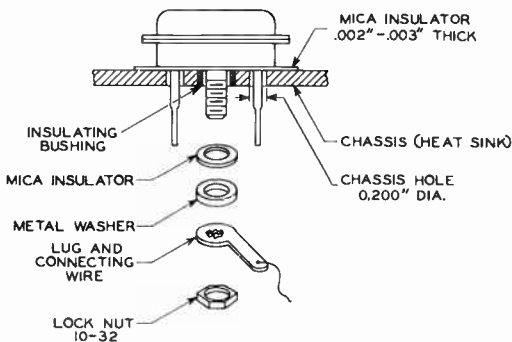


# 2N441



92CM-10612RI

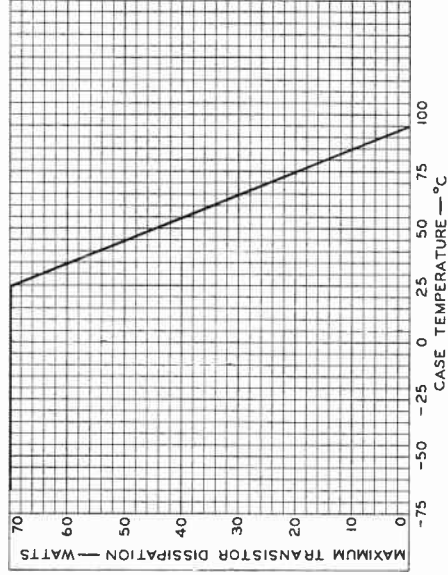
## SUGGESTED MOUNTING ARRANGEMENT



92CS-10624RI

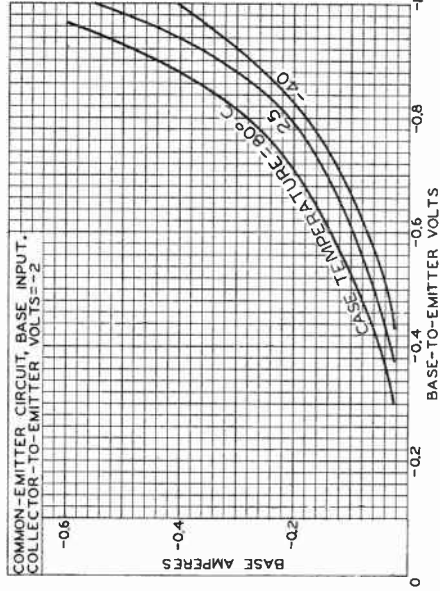


## RATING CHART



92CS-10701

## TYPICAL BASE CHARACTERISTICS

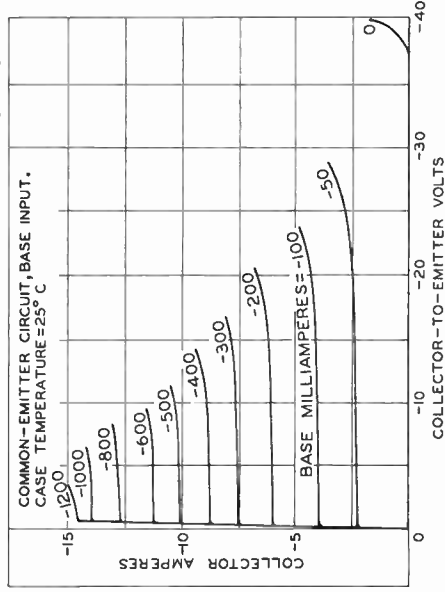


92CS-10717



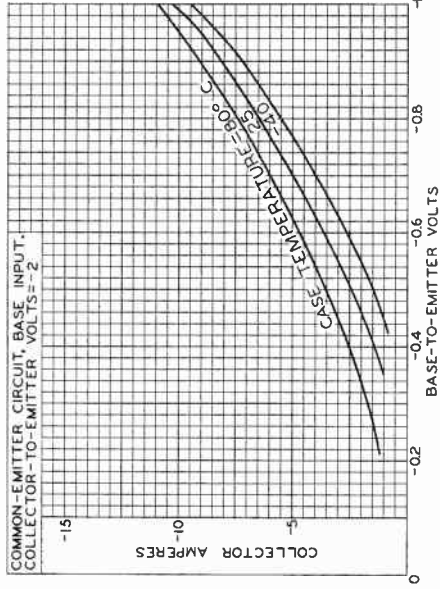
# 2N441

## TYPICAL COLLECTOR CHARACTERISTICS



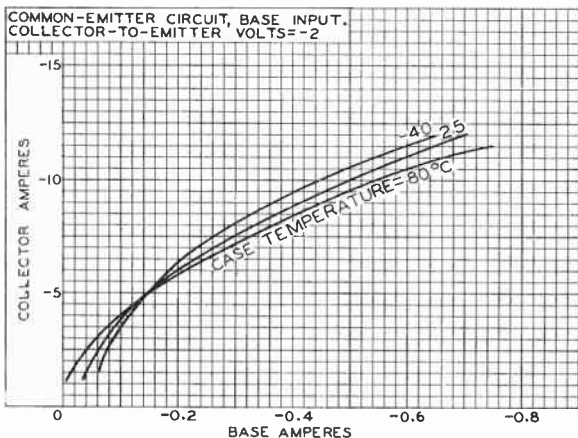
92CS-10732

## TYPICAL CHARACTERISTICS



92CS-10720

## TYPICAL CHARACTERISTICS



92CS-10721





## Power Transistor

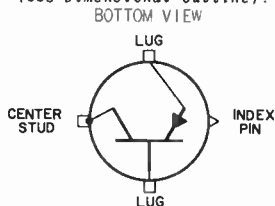
## GERMANIUM P-N-P ALLOY TYPE

For Power Switching and Amplifier Service  
in Industrial and Military Applications

## GENERAL DATA

## Mechanical:

Operating Position. . . . .	Any
Maximum Seated Length . . . . .	0.520"
Maximum Diameter. . . . .	1.250"
Dimensional Outline . . . . .	JEDEC No. TO-36
Case. . . . .	Welded, Metal
Seals . . . . .	Hermetic
Terminal Diagram (See Dimensional Outline):	



## INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter, chopper,  
voltage- and current-regulator, dc- and audio-  
amplifier, relay- and solenoid-actuating circuits

## Maximum and Minimum Ratings, Absolute-Maximum Values:

## COLLECTOR-TO-BASE VOLTAGE:

With emitter-to-base reverse biased

(DC emitter-to-base volts = -1.5) . . . . . -50 max. volts

EMITTER-TO-BASE VOLTAGE . . . . . -30 max. volts

COLLECTOR CURRENT . . . . . -15 max. amp

EMITTER CURRENT . . . . . 15 max. amp

BASE CURRENT. . . . . -4 max. amp

TRANSISTOR DISSIPATION:<sup>a</sup>

At case temperatures<sup>b</sup> of 25° C or below. . . . . 150 max. watts

CASE-TEMPERATURE<sup>b</sup> RANGE:

Operating and storage . . . . . -65 to +100 °C

## Typical Operation:

In a common-emitter, base-input, power-switching  
circuit at case temperature<sup>b</sup> of 25° C

DC Supply Voltage . . . . . -12 volts

DC Base-Bias Voltage. . . . . 6 volts

"On" DC Collector Current . . . . . -12 amp

"Turn-On" Base Current. . . . . -2 amp

"Turn-Off" Base Current . . . . . 0 amp

← Indicates a change.



RADIO CORPORATION OF AMERICA

Semiconductor & Materials Division

Somerville, N. J.

DATA 1

8-61

# 2N442

## Switching Time:

Rise time . . . . .	15	$\mu$ sec
Fall time . . . . .	15	$\mu$ sec

<sup>a</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

<sup>b</sup> Measured at any point on seating surface.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and at case temperature<sup>b</sup> of 25° C unless otherwise specified

Min. Typical Max.

### DC Collector-to-Emitter

#### Breakdown Voltage:

With base connected to emitter, dc collector

amperes = -0.3. . . . .  $BV_{CES}$  -45 - - volts

With base open:

For dc collector amperes = -0.3. . . . .  $BV_{CEO}$  - -45 - volts

For dc collector amperes = -1<sup>c</sup>. . . . . -30 - - volts

### DC Base-to-Emitter

Voltage for dc collector-to-emitter volts = -2, dc collector

amperes = -5. . . . .  $V_{BE}$  - -0.65 - volt

### DC Collector-to-Emitter

Saturation Voltage for dc collector

amperes = -12, dc base amperes = -2. . . . .  $V_{CE(sat)}$  - -0.3 - volt

### DC Emitter Voltage for

dc collector volts = -50, dc emitter current

= 0. . . . .  $V_{EB}$  - - -1 volt

### DC Punch-Through Voltage.

for dc emitter volts = -30, dc collector current = 0. . . . .  $V_{PT}$  -50 - - volts

### DC Emitter-Cutoff Current

for dc emitter volts = -30, dc collector current = 0. . . . .  $I_{EBO}$  - -1 -4 ma

### DC Collector-Cutoff

Current:  $I_{CBO}$

With dc collector volts = -2, dc emitter current = 0. . . . . - -100 -  $\mu$ a

With dc collector volts = -50, dc emitter current = 0. . . . . - -2 -4 ma

With dc collector volts = -50, dc emitter current = 0, case temperature<sup>b</sup> = 71° C. . . . . - - -15 ma

→ Indicates a change.





DC Current Transfer Ratio for dc collector-to-emitter volts = -2, dc collector amperes =	$h_{FE}$			
-5 . . . . .		20	-	40
-12 . . . . .		-	20	-
Beta-Cutoff Frequency for dc collector-to-emitter volts = -6, dc collector amperes = -5 . . . . .	$f_{ae}$	-	10	-
Thermal Resistance: Junction-to-case . . . . .	$R_T$	-	0.35	0.5 °C/watt
Thermal Capacity for pulse duration of 1 to 10 milliseconds . . . . .		-	0.075	-
Thermal Time Constant . . . . .	$\tau_1$	-	26.25	-

<sup>b</sup> Measured at any point on seating surface.

<sup>c</sup> Tested by sweep method to prevent excessive heating of collector junction.

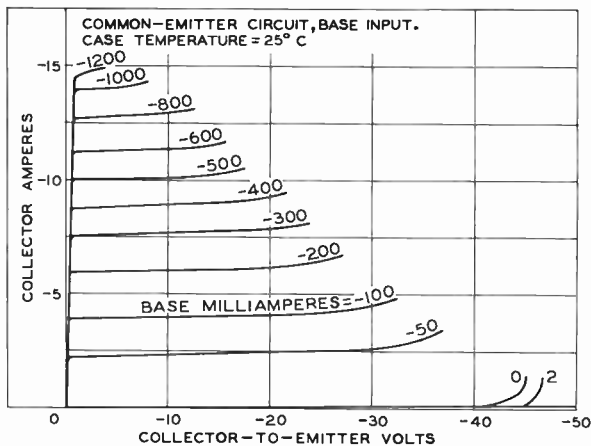
PERFORMANCE TESTS,  
 OPERATING CONSIDERATIONS,  
 DIMENSIONAL OUTLINE,  
 SUGGESTED MOUNTING ARRANGEMENT,  
 RATING CHART,  
 TYPICAL BASE-CHARACTERISTICS CURVES,  
 and  
 TYPICAL CHARACTERISTICS CURVES  
 shown under Type 2N441 also apply to the 2N442

← Indicates a change.



# 2N442

## TYPICAL COLLECTOR CHARACTERISTICS



92CS-10739



## Power Transistor

## GERMANIUM P-N-P ALLOY TYPE

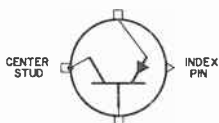
For Power Switching and Amplifier Service  
in Industrial and Military Applications

## GENERAL DATA

## Mechanical:

Operating Position . . . . .	Any
Maximum Overall Length . . . . .	1.230"
Maximum Seated Length . . . . .	0.520"
Maximum Diameter . . . . .	1.250"
Dimensional Outline . . . . .	JEDEC No. TO-36
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic
Terminal Diagram (See Dimensional Outline):	

## BOTTOM VIEW



## INDUSTRIAL SERVICE

*Such as in dc-to-dc converter, inverter, chopper,  
voltage- and current-regulator, dc- and audio  
amplifier, relay- and solenoid-actuating circuits*

## Maximum and Minimum Ratings, Absolute-Maximum Values:

## COLLECTOR-TO-BASE VOLTAGE:

With emitter-to-base reverse biased

(DC emitter-to-base volts = -1.5) . . . . . -50 max. volts

EMITTER-TO-BASE VOLTAGE . . . . . -30 max. volts

COLLECTOR CURRENT . . . . . -15 max. amp

EMITTER CURRENT . . . . . 15 max. amp

BASE CURRENT . . . . . -4 max. amp

TRANSISTOR DISSIPATION:<sup>▲</sup>

At case temperature of 25° C. . . . . 70 max. watts

## CASE-TEMPERATURE RANGE:

Continuous operation . . . . . -65 to +95 °C

Intermittent operation . . . . . -65 to +100 °C

Storage . . . . . -65 to +100 °C

## Typical Operation:

*In a common-emitter, base-input, power-  
switching circuit at case temperature of 25° C*

DC Supply Voltage . . . . . -12 volts

DC Base-Bias Voltage . . . . . 6 volts

"On" DC Collector Current . . . . . -12 amp

"Turn-On" Base Current . . . . . -2 amp

"Turn-Off" Base Current . . . . . 0 amp



# 2N442

## Switching Time:

Rise time . . . . .	15	$\mu$ SEC
Fall time . . . . .	15	$\mu$ SEC

▲ See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and case temperature of 25° C unless otherwise specified

Min. Typical Max.

### DC Collector-to-Emitter

#### Breakdown Voltage:

With base connected to emitter, dc collector

amperes = -0.3 . . .  $BV_{CES}$  -45 - - volts

With base open:  $BV_{CEO}$

For dc collector amperes = -0.3 . . . - -45 - volts

For dc collector amperes = -1 . . . -30 - - volts

### DC Base-to-Emitter

Voltage\* for dc collector-to-emitter volts = -2, dc collector

amperes = -5 . . .  $V_{BE}$  - -0.65 - volt

### DC Collector-to-Emitter

#### Saturation Voltage\*

for dc collector amperes = -12, base

amperes = -2 . . .  $V_{CE}$  - -0.3 - volt

### DC Emitter Voltage for

dc collector volts = -50, dc emitter amperes

= 0 . . .  $V_{EB}$  - - -1 - volt

### DC Punch-Through Voltage:

$V_P$  -50 - - - volts

### DC Emitter-Cutoff Current

for dc emitter volts =

-30, dc collector amperes = 0 . . .  $I_{EBO}$  - -1 -8 ma

### DC Collector-Cutoff

Current:  $I_{CBO}$

With dc collector volts = -2, dc emitter amperes = 0 . . . - -100 -  $\mu$ a

With dc collector volts = -50, dc emitter amperes = 0 . . . - -2 -8 ma

With dc collector volts = -50, dc emitter amperes = 0, case

temperature = 71° C . . . - - -15 ma



DC Current Transfer Ratio\*  $h_{FE}$

for dc collector-to-emitter volts = -2, dc collector amperes =

-5 . . . . .	20	-	40
-12 . . . . .	-	20	-

Beta-Cutoff Frequency\*

for dc collector-to-emitter volts = -6, dc collector amperes = -5 .  $f_{ae}$

Thermal Resistance:

Junction-to-case . . . .  $R_T$  - 0.7 1 °C/watt

Thermal Capacity for pulse

duration of 1 to 10 milliseconds . . . . . - 0.075 - watt-sec/°C

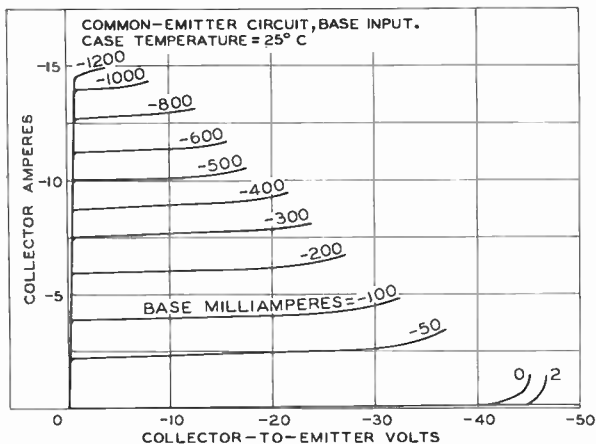
Thermal Time Constant . . .  $\tau_1$  - 52.5 - msec

• Sweep voltage used to perform test.

\* Measured in a common-emitter, base-input circuit.

OPERATING CONSIDERATIONS,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHART,  
TYPICAL BASE-CHARACTERISTICS CURVES,  
and TYPICAL CHARACTERISTICS CURVES  
shown under Type 2N441 also apply to the 2N442

## TYPICAL COLLECTOR CHARACTERISTICS





## Power Transistor

## GERMANIUM P-N-P ALLOY TYPE

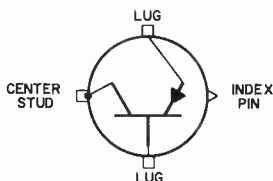
For Power Switching and Amplifier Service  
in Industrial and Military Applications

## GENERAL DATA

## Mechanical:

Operating Position. . . . .	Any
Maximum Seated Length . . . . .	0.520"
Maximum Diameter. . . . .	1.250"
Dimensional Outline . . . . .	JEDEC No. TO-36
Case. . . . .	Welded, Metal
Seals . . . . .	Hermetic
Terminal Diagram (See <i>Dimensional Outline</i> ):	

BOTTOM VIEW



## INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter, chopper,  
voltage- and current-regulator, dc- and audio-  
amplifier, relay- and solenoid-actuating circuits

## Maximum and Minimum Ratings, Absolute-Maximum Values:

## COLLECTOR-TO-BASE VOLTAGE:

With emitter-to-base reverse biased

(DC emitter-to-base volts = -1.5) . . . . . -60 max. volts

EMITTER-TO-BASE VOLTAGE . . . . . -40 max. volts

COLLECTOR CURRENT . . . . . -15 max. amp

EMITTER CURRENT . . . . . 15 max. amp

BASE CURRENT. . . . . -4 max. amp

TRANSISTOR DISSIPATION:<sup>a</sup>

At case temperatures<sup>b</sup> of 25°C or below. . . . . 150 max. watts

CASE-TEMPERATURE<sup>b</sup> RANGE:

Operating and storage . . . . . -65 to +100 °C

## Typical Operation:

In a common-emitter, base-input, power-  
switching circuit at case temperature<sup>b</sup> of 25°C

DC Supply Voltage . . . . . -12 volts

DC Base-Bias Voltage. . . . . 6 volts

"On" DC Collector Current . . . . . -12 amp

"Turn-On" Base Current. . . . . -2 amp

"Turn-Off" Base Current . . . . . 0 amp

← Indicates a change.



# 2N443

## Switching Time:

Rise time . . . . .	15	$\mu$ sec
Fall time . . . . .	15	$\mu$ sec

<sup>a</sup> See accompanying *Rating Chart* and also *Transistor-Dissipation Rating Chart* in General Section.

<sup>b</sup> Measured at any point on seating surface.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and at case temperature<sup>b</sup> of 25° C unless otherwise specified

Min. Typical Max.

### DC Collector-to-Emitter

#### Breakdown Voltage:

With base connected to emitter, dc collector

amperes = -0.3. . . . .  $V_{V_{CES}}$  -50 - - volts

With base open:

For dc collector amperes = -0.3. . . . .  $V_{V_{CEO}}$  - - -55 - volts

For dc collector amperes = -1<sup>c</sup>. . . . . -45 - - volts

### DC Base-to-Emitter

Voltage for dc collector-to-emitter

volts = -2, dc collector amperes = -5. . . . .  $V_{V_{BE}}$  - -0.65 -0.9 volt

### DC Collector-to-Emitter

Saturation Voltage

for dc collector amperes = -12, dc base amperes = -2. . . . .  $V_{V_{CE}}$  - -0.3 -1 volt

### DC Emitter Voltage for dc

collector volts = -60, dc emitter current = 0. . . . .  $V_{V_{EB}}$  - - -1 volt

### DC Punch-Through Voltage.

$V_{V_{PT}}$  -60 - - volts

### DC Emitter-Cutoff Current

for dc emitter volts = -40, dc collector current = 0. . . . .  $I_{I_{EBO}}$  - -1 -4 ma

### DC Collector-Cutoff

Current:  $I_{I_{CBO}}$

With dc collector volts = -2, dc emitter current = 0. . . . . - -100 -  $\mu$ a

With dc collector volts = -60, dc emitter current = 0. . . . . - -2 -4 ma

With dc collector volts = -60, dc emitter current = 0, case temperature<sup>b</sup> = 71° C. . . . . - - -15 ma

→ Indicates a change.





DC Current Transfer Ratio for dc collector-to-emitter volts = -2, dc collector amperes =	$h_{FE}$				
-5 . . . . .		20	-	40	
-12 . . . . .		-	20	-	
Beta-Cutoff Frequency for dc collector-to-emitter volts = -6, dc collector amperes = -5 . . . . .	$f_{ae}$	-	10	-	kc
Thermal Resistance: Junction-to-case . . . . .	$R_T$	-	0.35	0.5	$^{\circ}\text{C}/\text{watt}$
Thermal Capacity for pulse duration of 1 to 10 milliseconds . . . . .		-	0.075	-	$\text{watt-sec}/^{\circ}\text{C}$ msec
Thermal Time Constant . . . . .	$\tau_1$	-	26.25	-	msec

<sup>b</sup> measured at any point on seating surface.

<sup>c</sup> Tested by sweep method to prevent excessive heating of collector junction.

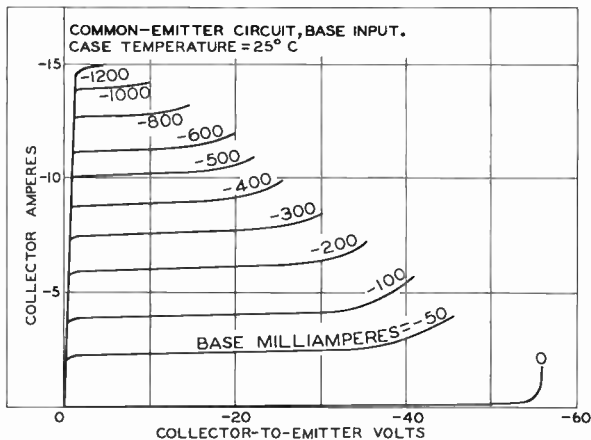
**PERFORMANCE TESTS,**  
**OPERATING CONSIDERATIONS,**  
**DIMENSIONAL OUTLINE,**  
**SUGGESTED MOUNTING ARRANGEMENT,**  
**RATING CHART,**  
**TYPICAL BASE-CHARACTERISTICS CURVES,**  
 and  
**TYPICAL CHARACTERISTICS CURVES**  
 shown under Type 2N441 also apply to the 2N443

← Indicates a change.



# 2N443

## TYPICAL COLLECTOR CHARACTERISTICS



92CS-10729



## Power Transistor

GERMANIUM P-N-P ALLOY TYPE

For Power Switching and Amplifier Service  
in Industrial and Military Applications

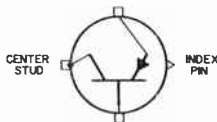
### GENERAL DATA

#### Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	1.230"
Maximum Seated Length. . . . .	0.520"
Maximum Diameter. . . . .	1.250"
Dimensional Outline. . . . .	JEDEC No. TO-36
Case. . . . .	Welded, Metal
Seals. . . . .	Hermetic

Terminal Diagram (See *Dimensional Outline*):

BOTTOM VIEW



### INDUSTRIAL SERVICE

*Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and audio amplifier, relay- and solenoid-actuating circuits*

#### Maximum and Minimum Ratings, Absolute Maximum Values:

##### COLLECTOR-TO-BASE VOLTAGE:

With emitter-to-base reverse biased

(DC emitter-to-base volts = -1.5) . . . . . -60 max. volts

EMITTER-TO-BASE VOLTAGE. . . . . -40 max. volts

COLLECTOR CURRENT. . . . . -15 max. amp

EMITTER CURRENT. . . . . 15 max. amp

BASE CURRENT. . . . . -4 max. amp

##### TRANSISTOR DISSIPATION:<sup>A</sup>

At case temperature of 25° C . . . . . 70 max. watts

##### CASE-TEMPERATURE RANGE:

Continuous operation . . . . . -65 to +95 °C

Intermittent operation . . . . . -65 to +100 °C

Storage. . . . . -65 to +100 °C

#### Typical Operation:

*In a common-emitter, base-input, power-switching circuit at case temperature of 25° C*

DC Supply Voltage. . . . . -12 volts

DC Base-Bias Voltage . . . . . 6 volts

"On" DC Collector Current. . . . . -12 amp

"Turn-On" Base Current . . . . . -2 amp

"Turn-Off" Base Current. . . . . 0 amp



# 2N443

## Switching Time:

Rise time . . . . .	15	$\mu$ sec
Fall time . . . . .	15	$\mu$ sec

▲ See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and case temperature of 25° C unless otherwise specified  
Min. Typical Max.

DC Collector-to-Emitter Breakdown Voltage:					
With base connected to emitter, dc collector amperes = -0.3 . . .	$BV_{CES}$	-50	-	-	volts
With base open:	$BV_{CEO}$				
For dc collector amperes = -0.3 . . .		-	-55	-	volts
For dc collector amperes = -1 . . .		-45	-	-	volts
DC Base-to-Emitter Voltage* for dc collector-to-emitter volts = -2, dc collector amperes = -5 . . .	$V_{BE}$	-	-0.65	-0.9	volt
DC Collector-to-Emitter Saturation Voltage* for dc collector amperes = -12, base amperes = -2 . . . . .	$V_{CE}$	-	-0.3	-1	volt
DC Emitter Voltage for dc collector volts = -60, dc emitter amperes = 0.	$V_{EB}$	-	-	-1	volt
DC Punch-Through Voltage.	$V_P$	-60	-	-	volts
DC Emitter-Cutoff Current for dc emitter volts = -40, dc collector amperes = 0 . . . . .	$I_{EBO}$	-	-1	-8	ma
DC Collector-Cutoff Current:	$I_{CBO}$				
With dc collector volts = -2, dc emitter amperes = 0 . . . . .		-	-100	-	$\mu$ a
With dc collector volts = -60, dc emitter amperes = 0 . . . . .		-	-2	-8	ma
With dc collector volts = -60, dc emitter amperes = 0, case temperature = 71° C .		-	-	-15	ma



# 2N443

DC Current Transfer Ratio* for dc collector-to-emitter volts = -2, dc collector amperes =	$h_{FE}$			
-5 . . . . .		20	-	40
-12 . . . . .		-	20	-
Beta-Cutoff Frequency* for dc collector-to-emitter volts = -6, dc collector amperes = -5 . . . . .	$f_{\alpha e}$	-	10	-
				kc
Thermal Resistance: Junction-to-case . . . . .	$R_T$	-	0.7	1
				$^{\circ}\text{C}/\text{watt}$
Thermal Capacity for pulse duration of 1 to 10 milliseconds . . . . .		-	0.075	-
				watt-sec/ $^{\circ}\text{C}$
Thermal Time Constant . . . . .	$\tau_1$	-	52.5	-
				msec

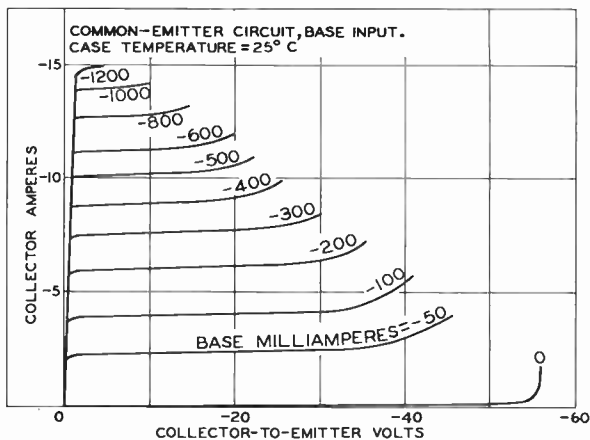
• Sweep voltage used to perform test.

\* Measured in a common-emitter, base-input circuit.

OPERATING CONSIDERATIONS,  
 DIMENSIONAL OUTLINE,  
 SUGGESTED MOUNTING ARRANGEMENT,  
 RATING CHART,  
 TYPICAL BASE-CHARACTERISTICS CURVES,  
 and TYPICAL CHARACTERISTICS CURVES  
 shown under Type 2N441 also apply to the 2N443



## TYPICAL COLLECTOR CHARACTERISTICS



92CS-10729

## Power Transistor

## SILICON N-P-N DIFFUSED-JUNCTION TYPE

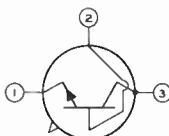
For Medium-Power Switching and Amplifier  
Service in Industrial and Military Applications

## GENERAL DATA

## Mechanical:

Operating Position. . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter. . . . .	0.370"
Dimensional Outline . . . . .	JEDEC No. 10-5
Case. . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length. . . . .	1.5"
Orientation and diameter. . . . .	See Dimensional Outline
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector,  
Case

## INDUSTRIAL SERVICE

*Such as in dc-to-dc converter, inverter, chopper,  
voltage- and current-regulator, dc- and servo-  
amplifier, relay- and solenoid-actuating circuits*

## Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE. . . . .	60 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With base open . . . . .	60 max.	volts
EMITTER-TO-BASE VOLTAGE. . . . .	8 max.	volts
TRANSISTOR DISSIPATION: <sup>a</sup>		
At case temperature of 25° C . . . . .	4 max.	watts
At case temperature of 100° C. . . . .	2.28 max.	watts
CASE-TEMPERATURE RANGE:		
Operating and storage. . . . .	-65 to +200	°C

<sup>a</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## ELECTRICAL CHARACTERISTICS

*Voltage values are given with respect to base unless  
otherwise specified. Ambient temperature of 25° C.*

*Min. Typical Max.*

DC Collector Breakdown Volt- age for dc collector ma. = 0.1, dc emitter ma. = 0.	$BV_{CBO}$	60	-	-	volts
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# 2N497

		Min.	Typical	Max.	
DC Collector-to-Emitter Breakdown Voltage for dc collector ma. = 0.25, dc base ma. = 0. . . .	$BV_{CEO}$	60	-	-	volts
DC Emitter Breakdown Voltage for dc emitter ma. = 0.25, dc collector ma. = 0. . . .	$BV_{EBO}$	8	-	-	volts
DC Collector-Cutoff Current for dc collector volts = 30, dc emitter ma. = 0. . . .	$I_{CBO}$	-	-	10	$\mu$ a
DC Current Transfer Ratio for dc collector-to-emitter volts = 10, dc collector ma. = 200 . . . .	$h_{FE}$	12	-	36	
Input Resistance for dc collector-to-emitter volts = 10, dc collector ma. = 200 . . . .	$h_{iE}$	-	-	500	ohms
DC Collector-to-Emitter Saturation Resistance for dc collector ma. = 200, dc base ma. = 20. . . .	$R_S$	-	-	25	ohms
Thermal Resistance: Between junction and case . . . . .	$R_T$	-	-	43.75	$^{\circ}C/watt$
Between junction and free air . . . . .		-	-	200	$^{\circ}C/watt$
Thermal Time Constant. . . . .	$\tau_1$	-	10	-	msec

## OPERATING CONSIDERATIONS

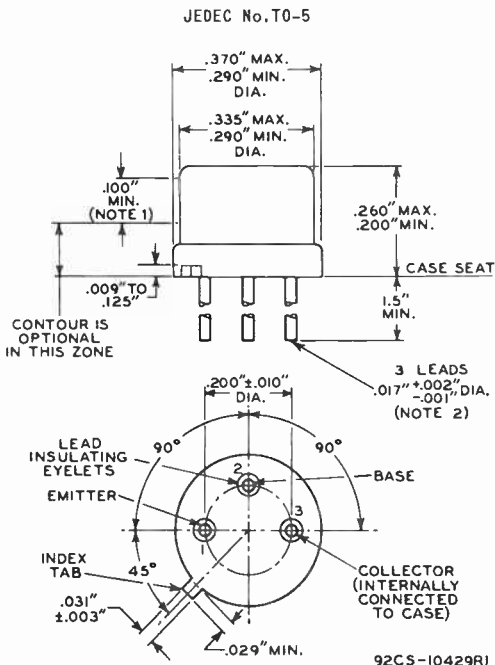
It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible Leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.

It is to be noted that the case of this transistor operates at the collector voltage. Consideration, therefore, should be given to the possibility of shock hazard, if the case of this transistor is to operate at a voltage appreciably above or below ground potential. In such cases, suitable precautionary measures should be taken.





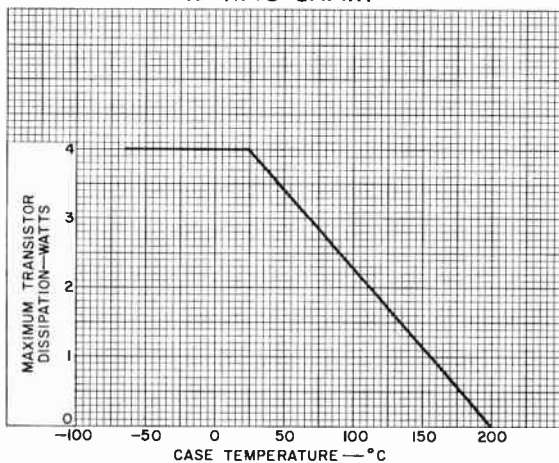


NOTE 1: THE DIAMETER IN THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE TOTAL VARIATION IN ACTUAL DIAMETER FROM THE TRUE DIAMETER, DUE TO TAPER AND OUT OF ROUND WITHIN THIS ZONE, WILL NOT EXCEED 0.010".

NOTE 2: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE CASE SEAT. BETWEEN 0.25" AND 1.5", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

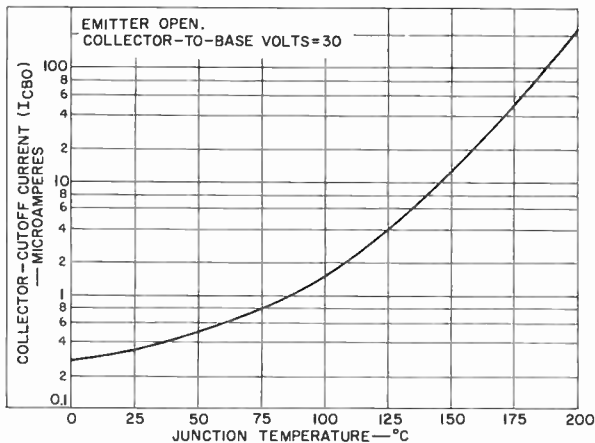


## RATING CHART



92CS-10854

## TYPICAL OPERATION CHARACTERISTIC



92CS-10841



2N544

# 2N544

## DRIFT TRANSISTOR

GERMANIUM P-N-P ALLOY TYPE

For radio-frequency amplifier applications

### GENERAL DATA

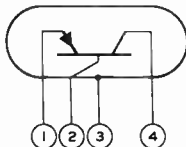
Electrical, At Ambient Temperature of 25° C:

Minimum DC Collector-to-Base Voltage for dc collector current of -50 $\mu$ a with emitter open. . . . .	-18	volts
Maximum DC Collector Current for dc collector-to-base voltage of -12 volts with emitter open. . . . .	-4	$\mu$ a
Maximum DC Emitter Current for dc emitter-to-base voltage of -1 volt with collector open. . . . .	-12	$\mu$ a
Interlead Capacitance between col- lector and base leads with inter- lead shield connected to ground and all leads cut to 5/16" . . . . .	0.03	$\mu$ f

### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads). . . . .	0.375"
Maximum Diameter . . . . .	0.360"
Case . . . . .	Metal
Envelope Seals . . . . .	Hermetic
Leads, Flexible. . . . .	4
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See Dimensional Outline

Lead 1 - Emitter



Lead 2 - Base

Lead 3 - interlead  
Shield,  
Metal  
Case

Lead 4 - Collector

### RADIO-FREQUENCY AMPLIFIER — Class A

Maximum Ratings, Absolute Values:

COLLECTOR-TO-BASE VOLTAGE (DC + Peak AC) . . . . .	-18 max.	volts
EMITTER-TO-BASE VOLTAGE (DC + Peak AC) . . . . .	-1 max.	volt
DC COLLECTOR CURRENT . . . . .	-10 max.	ma
DC EMITTER CURRENT . . . . .	10 max.	ma
COLLECTOR DISSIPATION:		
At ambient temperature of 25° C. . . . .	80 max.	mw
At ambient temperature of 55° C. . . . .	50 max.	mw
At ambient temperature of 71° C. . . . .	35 max.	mw
AMBIENT TEMPERATURE (During operation) . . . . .	71 max.	°C
STORAGE-TEMPERATURE RANGE. . . . .	-65 to +85	°C



## 2N544

## DRIFT TRANSISTOR

Characteristics, At Ambient Temperature of 25° C:

Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage . . . . .	-12	volts
DC Emitter Current . . . . .	1	ma
Current Transfer Ratio ( $\alpha_f$ ) <sup>■</sup> . . . . .	-60	

Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage . . . . .	-12	volts
DC Emitter Current . . . . .	1	ma
Current Transfer Ratio ( $\alpha_f$ ) <sup>■</sup> . . . . .	0.984	
Alpha-Cutoff Frequency . . . . .	30	Mc

Typical Operation, At Ambient Temperature of 25° C:

At frequency of	1.5	1.5	1.5	Mc
DC Collector-to-Emitter Voltage . . . . .	-6	-9	-12	volts
DC Emitter Current . . . . .	0.5	0.5	0.5	ma
Input Resistance, ac output circuit shorted . . . . .	1300	1700	2100	ohms
Output Resistance, ac input circuit shorted . . . . .	0.11	0.18	0.28	megohm
Intrinsic Transconductance . . . . .	18900	18900	18900	$\mu$ hos
Collector-to-Base Capacitance . . . . .	1.85	1.65	1.55	$\mu$ mf
Maximum Power Gain <sup>▲</sup> . . . . .	41.1	44.4	47.3	db
Useful Power Gain:				
In neutralized circuit . . . . .	30.4	30.4	30.4	db
In unneutralized circuit . . . . .	25.1	25.1	25.1	db

■ Measured at 1 kc.

▲ Measured in a single-tuned unilateralized circuit matched to the generator and load impedances for maximum transfer of power. Transformer insertion losses not included.

## OPERATING CONSIDERATIONS

The 2N544 should not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The flexible leads of the 2N544 are usually soldered to the circuits elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

The 2N544 utilizes shielding to minimize interlead capacitance and to minimize coupling to adjacent circuit components. This shielding is provided by lead 3 (center lead) situated between the collector lead and the base lead and internally connected to the metal case. For optimum performance, it is recommended that lead 3 be connected to the circuit ground.

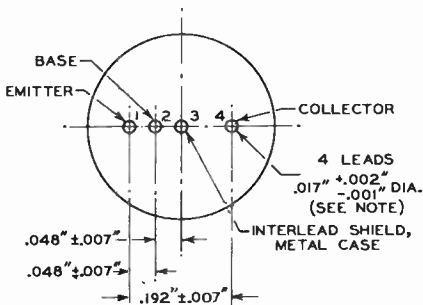
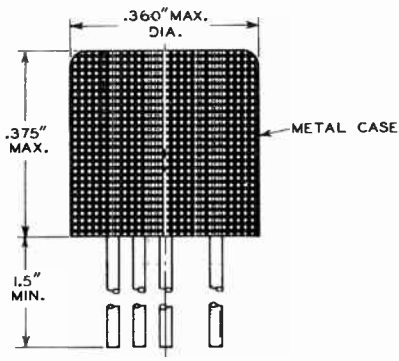
When dip soldering is employed in the assembly of printed circuitry using the 2N544, the temperature of the solder should not exceed 230° C for a maximum immersion period of 10 seconds.



2N544

DRIFT TRANSISTOR

2N544



92CS-9122R3

NOTE: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.050" AND 0.250" FROM THE BASE SEAT. BETWEEN 0.250" AND 1.50", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

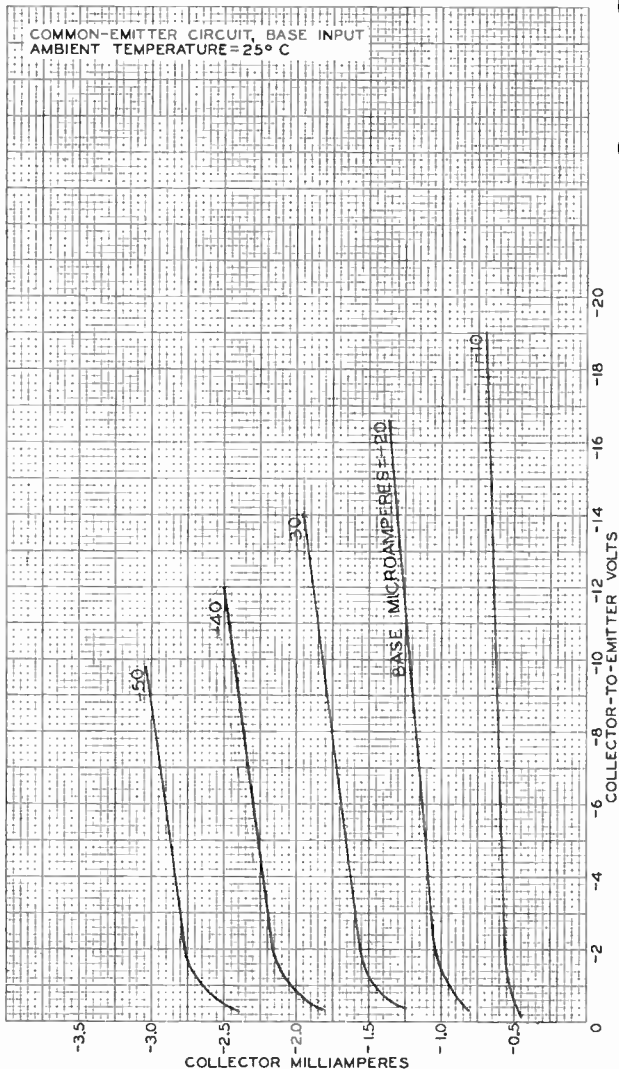
2N544



2N544

# AVERAGE COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
AMBIENT TEMPERATURE = 25° C

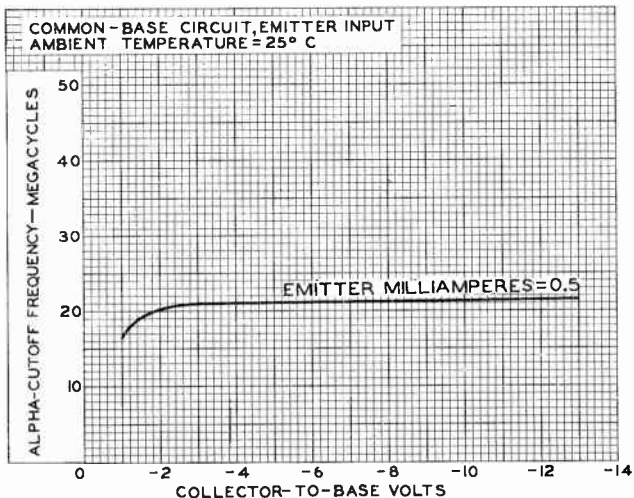




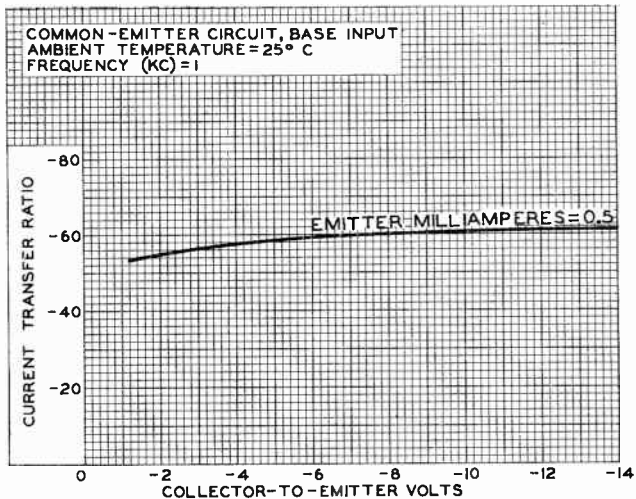
2N544

2N544

### AVERAGE CHARACTERISTICS



92CS-9514

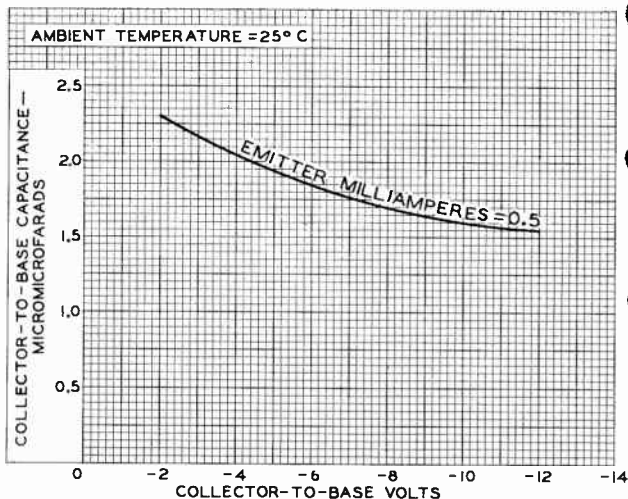


2N544

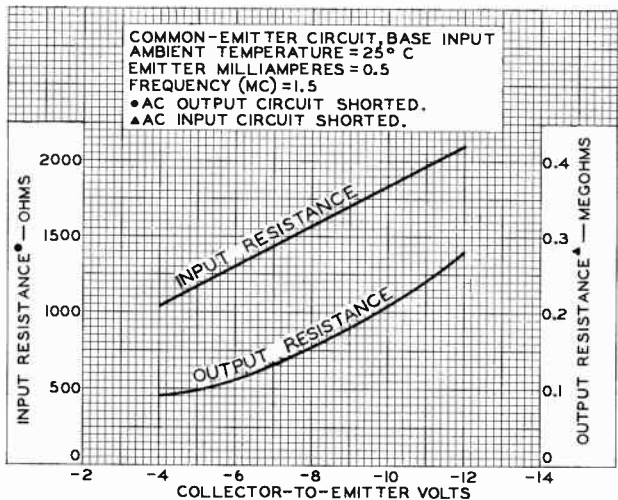


2N544

## AVERAGE CHARACTERISTICS



92CS-9516



92CS-9517



## Junction Transistor

## GERMANIUM P-N-P ALLOY TYPE

For Medium-Speed Switching Service in Commercial and Military Data-Processing Systems

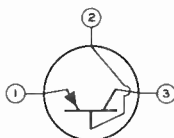
## GENERAL DATA

## Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter . . . . .	0.370"
Dimensional Outline . . . . .	JEDEC No. TO-9
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See Dimensional Outline
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base



Lead 3 - Collector

## SWITCHING SERVICE

## Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	-20 max.	volts	←
COLLECTOR-TO-EMITTER VOLTAGE:			
With emitter-to-base reverse biased			
(DC emitter-to-base volts = 1) . . . . .	-14 max.	volts	
EMITTER-TO-BASE VOLTAGE . . . . .	-12 max.	volts	
COLLECTOR CURRENT . . . . .	-400 max.	ma	
EMITTER CURRENT . . . . .	400 max.	ma	
TRANSISTOR DISSIPATION: <sup>a</sup>			
At ambient temperature of 25° C . . . . .	120 max.	mw	
At ambient temperature of 55° C . . . . .	35 max.	mw	
At ambient temperature of 71° C . . . . .	10 max.	mw	
AMBIENT TEMPERATURE (During operation) . . . . .	71 max.	°C	
STORAGE-TEMPERATURE RANGE . . . . .	-65 to +85	°C	
LEAD TEMPERATURE:			
For immersion in molten solder			←
for 10 seconds maximum . . . . .	255 max.	°C	

## Typical Operation:

In typical inverter circuit at ambient temperature of 25° C

"On" Collector Current . . . . .	-200	ma
"Turn-On" Base Current ( $I_{B1}$ ) . . . . .	-20	ma
"Turn-Off" Base Current ( $I_{B2}$ ) . . . . .	20	ma

← Indicates a change.



→ "Turn-On" Time . . . . .	0.6	μsec
"Turn-Off" Time . . . . .	0.6	μsec

<sup>a</sup> See transistor-Dissipation Rating Chart in General Section.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base unless otherwise specified. Ambient temperature of 25° C.

Min. Typical Max.

DC Collector Breakdown Voltage for dc collector ma. = -0.02, dc emitter ma. = 0 . . . . .	$BV_{CBO}$	-20	-30	-	volts
DC Emitter Breakdown Voltage for emitter ma. = 0.02, dc collec- tor ma. = 0 . . . . .	$BV_{EBO}$	-12	-20	-	volts
DC Punch-Through Voltage . . . . .	$V_P$	-15	-25	-	volts
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = -400, dc base ma. = -40 . . . . .	$V_{CE}$	-	-0.2	-0.3	volt
→ DC Base-to-Emitter Voltage for dc collec- tor ma. = -400, dc base ma. = -40 . . . . .	$V_{BE}$	-	-0.65	-1.2	volts
DC Collector-Cutoff Current for dc collec- tor volts = -12, dc emitter ma. = 0 . . . . .	$I_{CBO}$	-	-3	-5	μa
→ DC Emitter-Cutoff Current for dc emitter volts = -6, dc collector ma. = 0 . . . . .	$I_{EBO}$	-	-3	-	μa
DC Current Transfer Ratio for dc collector- to-emitter volts = -0.3, dc collector ma. = -400 . . . . .	$h_{FE}$	10	15	-	
Alpha-Cutoff Frequency for dc collector volts = -6, dc emitter ma. = 1 . . . . .	$f_{ab}$	3	5	-	Mc
→ Thermal Resistance be- tween collector junc- tion and free air . . . . .	$R_T$	-	-	500	°C/watt
→ Thermal Time Constant . . . . .	$\tau_1$	-	15	-	msec

## OPERATING CONSIDERATIONS

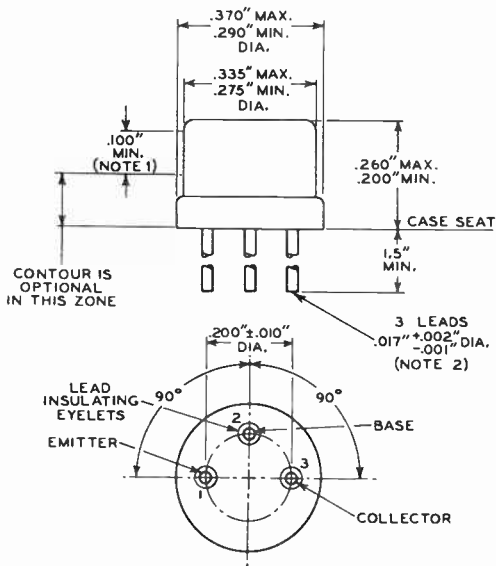
It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

→ Indicates a change.



The flexible leads of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.

## JEDEC No. T0-9



92CS-9371R7

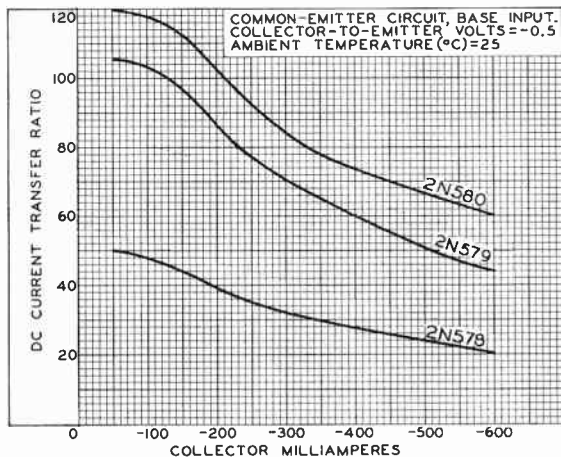
NOTE 1: THE DIAMETER IN THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE TOTAL VARIATION IN ACTUAL DIAMETER FROM THE TRUE DIAMETER, DUE TO TAPER AND OUT OF ROUND WITHIN THIS ZONE, WILL NOT EXCEED  $0.010$ ".

NOTE 2: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN  $0.05$ " AND  $0.25$ " FROM THE CASE SEAT. BETWEEN  $0.25$ " AND  $1.5$ ", A MAXIMUM DIAMETER OF  $0.021$ " IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

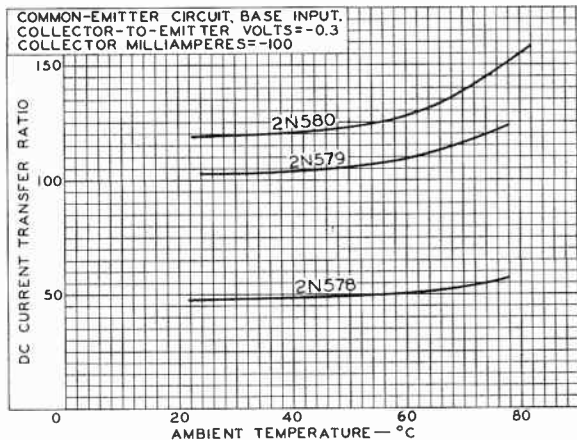


# 2N578

## TYPICAL CHARACTERISTICS

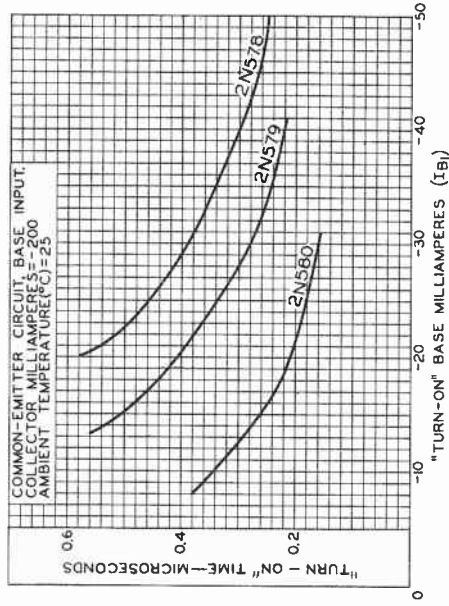


92CS-10861



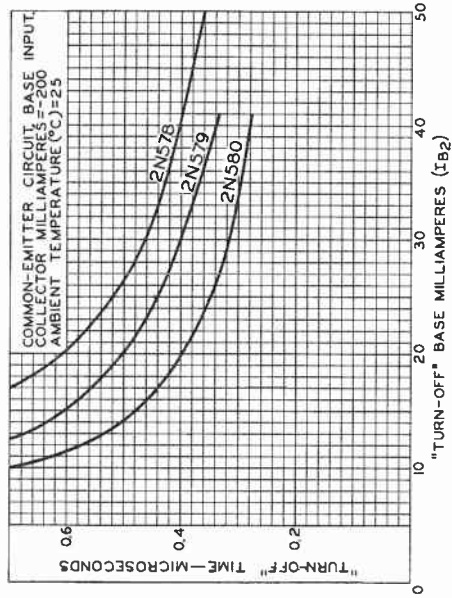
92CS-10862RI

## TYPICAL CHARACTERISTICS



World Precision Instrument

92CS-10863RI



92CS-10864





## Junction Transistor

## GERMANIUM P-N-P ALLOY TYPE

For Medium-Speed Switching Service in Commercial and Military Data-Processing Systems

The 2N579 is the same as the 2N578 except for the following items:

## Typical Operation:

In typical inverter circuit at ambient temperature of 25° C

"On" Collector Current. . . . .	-200	ma
"Turn-On" Base Current ( $I_{B1}$ ). . . . .	-20	ma
"Turn-Off" Base Current ( $I_{B2}$ ) . . . . .	20	ma
"Turn-On" Time. . . . .	0.4	$\mu$ sec
"Turn-Off" Time . . . . .	0.5	$\mu$ sec

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base unless otherwise specified. Ambient temperature of 25° C.

	Min.	Typical	Max.	
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = -400, dc base ma. = -20 . . . . . $V_{CE}$	-	-0.2	-0.3	volt
DC Base-to-Emitter Voltage for dc collector ma. = -400, dc base ma. = -20. . . . . $V_{BE}$	-	-0.63	-1.1	volts
DC Current Transfer Ratio for dc collector-to-emitter volts = -0.3, dc collector ma. = -400. . . . . $h_{FE}$	20	30	-	
Alpha-Cutoff Frequency for dc collector volts = -6, dc emitter ma. = 1 . . . . . $f_{\alpha b}$	5	8	-	Mc

## CURVES

for the 2N579 are given on the multi-type curve sheet under Type 2N578







## Junction Transistor

### GERMANIUM P-N-P ALLOY TYPE

For Medium-Speed Switching Service in Commercial and Military Data-Processing Systems

The 2N580 is the same as the 2N578 except for the following items:

#### Typical Operation:

In typical inverter circuit at ambient temperature of 25° C

"On" Collector Current. . . . .	-200	ma
"Turn-On" Base Current ( $I_{B1}$ ). . . . .	-20	ma
"Turn-Off" Base Current ( $I_{B2}$ ) . . . . .	20	ma
"Turn-On" Time. . . . .	0.2	$\mu$ sec
"Turn-Off" Time . . . . .	0.4	$\mu$ sec

### ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base unless otherwise specified. Ambient temperature of 25° C.

	Min.	Typical	Max.	
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = -400, dc base ma. = -13.3. . . . . $V_{CE}$	-	-0.2	-0.3	volt
DC Base-to-Emitter Voltage for dc collector ma. = -400, dc base ma. = -13.3 . . . . . $V_{BE}$	-	-0.6	-1	volt
DC Current Transfer Ratio for dc collector-to-emitter volts = -0.3, dc collector ma. = -400 . . . . . $h_{FE}$	30	45	-	
Alpha-Cutoff Frequency for dc collector volts = -6, dc emitter ma. = 1. . . . . $f_{ab}$	10	15	-	Mc

### CURVES

for the 2N580 are given on the multi-type curve sheet under Type 2N578





## Transistor

GERMANIUM P-N-P ALLOY-JUNCTION TYPE  
For Computer Switching Applications

### GENERAL DATA

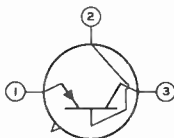
#### Mechanical:

Operating Position. . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter. . . . .	0.370"
Dimensional Outline . . . . .	JEDEC No. TO-5
Case. . . . .	Welded, Metal
Seal's . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length. . . . .	1.5"
Orientation and diameter. . . . .	See <i>Dimensional Outline</i>

#### Terminal Diagram:

#### BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector

### SWITCHING SERVICE

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	-18 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With dc emitter-to-base		
volts = -1. . . . .	-15 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-10 max.	volts
COLLECTOR CURRENT . . . . .	-100 max.	ma
EMITTER CURRENT . . . . .	100 max.	ma
TRANSISTOR DISSIPATION: <sup>a</sup>		
At ambient temperature of 25° C or below. . . . .	150 max.	mw
At ambient temperature of 55° C . . . . .	75 max.	mw
At ambient temperature of 71° C . . . . .	35 max.	mw
AMBIENT-TEMPERATURE RANGE:		
Operating . . . . .	-65 to +85	°C
Storage . . . . .	-65 to +100	°C
LEAD TEMPERATURE:		
For 10 seconds maximum. . . . .	255 max.	°C

<sup>a</sup> See accompanying *Rating Chart* and also *Transistor-Dissipation Rating Chart* in General Section.

← Indicates a change.



# 2N581

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base unless otherwise specified. Ambient temperature of 25° C.

Min. Typical Max.

DC Collector Breakdown Voltage for dc collector ma. = -0.02, dc emitter ma. = 0. . . . .	$BV_{CBO}$	-18	-30	-	volts
DC Punch-Through Voltage for dc emitter volts = -1. . . . .	$V_P$	-15	-25	-	volts
DC Emitter Breakdown Voltage for dc emitter ma. = -0.02, dc collector ma. = 0. . . . .	$BV_{EBO}$	-10	-25	-	volts
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = -20, dc base ma. = -1. . . . .	$V_{CE(sat)}$	-0.2	-0.3	-	volt
DC Base-to-Emitter Saturation Voltage for dc collector ma. = -20, dc base ma. = -1. . . . .	$V_{BE(sat)}$	-	-0.35	-0.5	volt
DC Collector-Cutoff Current for dc collector volts = -12, dc emitter ma. = 0. . . . .	$I_{CBO}$	-	-3	-10	$\mu$ a
DC Emitter-Cutoff Current for dc emitter volts = -2.5, dc collector ma. = 0. . . . .	$I_{EBO}$	-	-1	-	$\mu$ a
Collector-to-Base Capacitance for dc collector volts = -6, dc collector ma. = 0. . . . .	$C_{ob}$	-	12	20	$\mu$ mf
DC Current Transfer Ratio for dc collector-to-emitter volts = -0.3, dc collector ma. = -20 . . . . .	$h_{FE}$	20	30	-	
Alpha-Cutoff Frequency for dc collector volts = -6, dc collector ma. = -1 . . . . .	$f_{\alpha b}$	4	8	-	Mc
Stored Base Charge for dc collector ma. = -20, dc base ma. = -2. . . . .	$Q_S$	-	1700	2400	$\mu$ coulombs
Thermal Time Constant . . . . .	$\tau_1$	-	10	-	msec
Thermal Resistance: Junction-to-free air. . . . .	$R_T$	-	-	500	°C/watt

→ Indicates a change.



## PERFORMANCE TESTS

This transistor type is tested in accordance with Military Specification MIL-S-19500B.

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

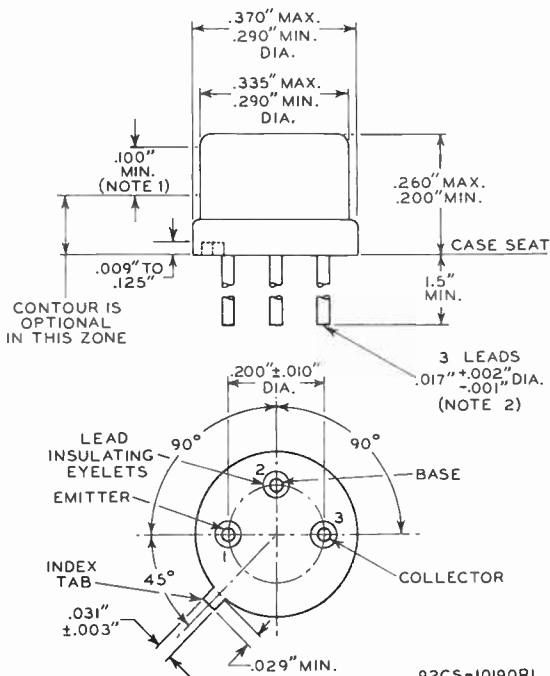
The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the seals of the leads and damage the transistor.

← Indicates a change.



# 2N581

JEDEC No. T0-5

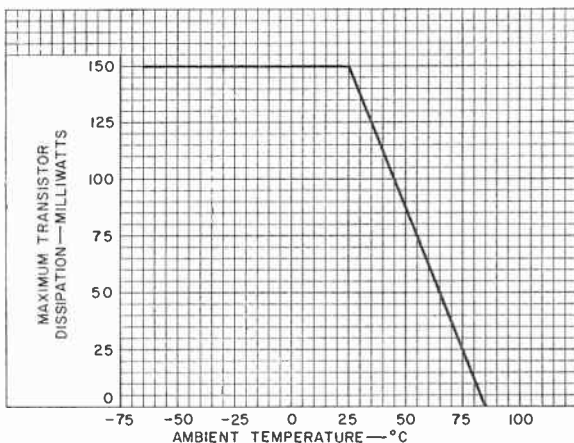


**NOTE 1:** THE DIAMETER IN THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE TOTAL VARIATION IN ACTUAL DIAMETER FROM THE TRUE DIAMETER, DUE TO TAPER AND OUT OF ROUND WITHIN THIS ZONE, WILL NOT EXCEED 0.010".

**NOTE 2:** THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE CASE SEAT. BETWEEN 0.25" AND 1.5", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.



## RATING CHART



92CS-10907RI







## Transistor

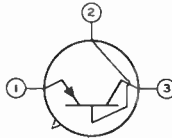
GERMANIUM P-N-P ALLOY-JUNCTION TYPE  
For Computer Switching Applications

### GENERAL DATA

#### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter . . . . .	0.370"
Dimensional Outline . . . . .	JEDEC No. TO-5
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector

### SWITCHING SERVICE

Maximum and Minimum Ratings, <i>Absolute-Maximum Values:</i>		
COLLECTOR-TO-BASE VOLTAGE . . . . .	-25 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With ac emitter-to-base volts = -1. . . . .	-14 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-12 max.	volts
COLLECTOR CURRENT . . . . .	-100 max.	ma
EMITTER CURRENT . . . . .	100 max.	ma
TRANSISTOR DISSIPATION: <sup>a</sup>		
At ambient temperature of 25° C or below . . . . .	150 max.	mw
At ambient temperature of 55° C . . . . .	75 max.	mw
At ambient temperature of 71° C . . . . .	35 max.	mw
AMBIENT-TEMPERATURE RANGE:		
Operating . . . . .	-65 to +85	°C
Storage . . . . .	-65 to +100	°C
LEAD TEMPERATURE:		
For 10 seconds maximum . . . . .	255 max.	°C

<sup>a</sup> See accompanying *Rating Chart* and also *Transistor-Dissipation Rating Chart* in General Section.

← Indicates a change.



# 2N582

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and at ambient temperature of 25°C unless otherwise specified

Min. Typical Max.

DC Collector Breakdown Voltage for dc collector ma. = -0.02, dc emitter ma. = 0 . . . . .	$BV_{CBO}$	-25	-30	-	volts
DC Punch-Through Voltage for dc emitter volts = -1 . . . . .	$V_P$	-14	-30	-	volts
DC Emitter Breakdown Voltage for dc emitter ma. = -0.02, dc collector ma. = 0 . . . . .	$BV_{EBO}$	-12	-30	-	volts
DC Collector-to-Emitter Saturation Voltage: $V_{CE(sat)}$ With dc collector ma. = -24, dc base ma. = -0.6 . . . . .		-	-0.12	-0.2	volt
With dc collector ma. = -100, dc base ma. = -5 . . . . .		-	-0.2	-0.3	volt
DC Base-to-Emitter Saturation Voltage: $V_{BE(sat)}$ With dc collector ma. = -24, dc base ma. = -0.6 . . . . .		-	-0.3	-0.4	volt
With dc collector ma. = -100, dc base ma. = -5 . . . . .		-	-0.6	-0.8	volt
DC Collector-Cutoff Current for dc collector volts = -12, dc emitter ma. = 0, ambient temperature = 25°C . . . . . 80°C . . . . .	$I_{CBO}$	-	-2 -45	-5 -90	$\mu a$ $\mu a$
DC Emitter-Cutoff Current for dc emitter volts = -2.5, dc collector ma. = 0 . . . . .	$I_{EBO}$	-	-1	-	$\mu a$
Collector-to-Base Capacitance for dc collector volts = -6, dc collector ma. = 0 . . . . .	$C_{ob}$	-	12	20	$\mu f$
DC Current Transfer Ratio: With dc collector-to-emitter volts = -0.2, dc collector ma. = -24 . . . . .	$h_{FE}$	40	60	-	

→ Indicates a change.



With dc collector-to-emitter volts = -0.3,					
dc collector ma. = -100. . . . .					
	20	25	-		
Alpha-Cutoff Frequency for dc collector volts = -6, dc collector ma. = -1. . . . .					
	$f_{ab}$	14	18	-	Mc
Stored Base Charge for dc collector ma. = -24, dc base ma. = -1.2 . . . .					
	$Q_S$	-	800	1200	$\mu\text{coulombs}$
Thermal Time Constant . . . . .					
	$\tau_I$	-	10	-	msec
Thermal Resistance:					
Junction-to-free air. . . . .					
	$R_T$	-	-	500	$^{\circ}\text{C/watt}$

### PERFORMANCE TESTS

This transistor type is tested in accordance with Military Specification MIL-S-19500B.

### OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

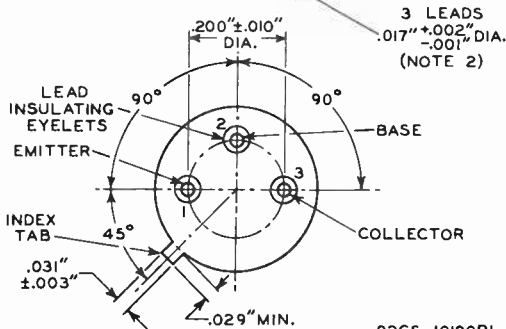
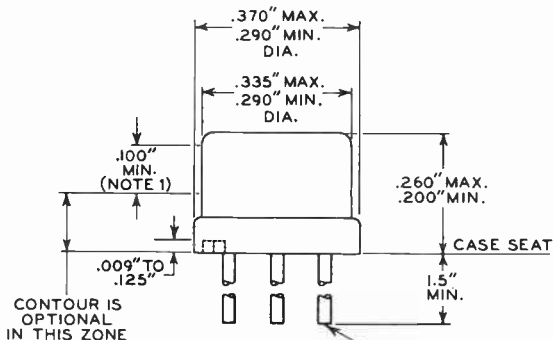
The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the seals of the leads and damage the transistor.

← Indicates a change.



# 2N582

JEDEC No. T0-5

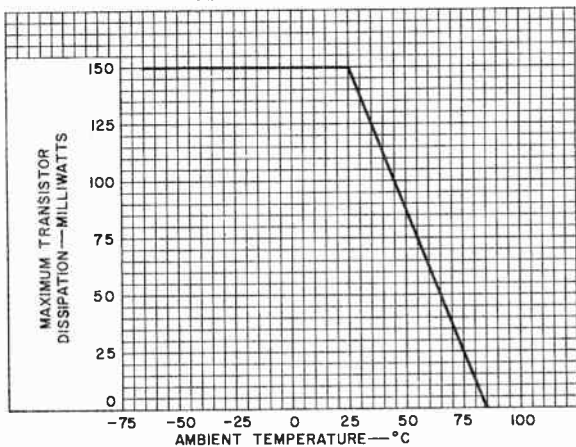


92CS-10190RI

NOTE 1: THE DIAMETER IN THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE TOTAL VARIATION IN ACTUAL DIAMETER FROM THE TRUE DIAMETER, DUE TO TAPER AND OUT OF ROUND WITHIN THIS ZONE, WILL NOT EXCEED 0.010".

NOTE 2: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE CASE SEAT. BETWEEN 0.25" AND 1.5", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

## RATING CHART



92CS-10907RI





## Transistor

GERMANIUM P-N-P ALLOY-JUNCTION TYPE  
For Computer Switching Applications

### GENERAL DATA

#### Mechanical:

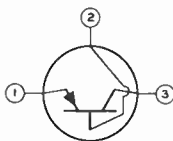
Operating Position . . . . .	Any	←
Maximum Length (Excluding flexible leads) . . . . .	0.410"	
Maximum Diameter . . . . .	0.240"	
Dimensional Outline . . . . .	JEDEC No. TO-1	
Case . . . . .	Metal	
Seals . . . . .	Hermetic	
Leads, Flexible . . . . .	3	
Minimum length . . . . .	1.5"	
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>	

Terminal Diagram:

BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base



Lead 3 - Collector  
(Adjacent to red dot on side of case)

### SWITCHING SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values:*

COLLECTOR-TO-BASE VOLTAGE . . . . .	-18 max.	volts	←
COLLECTOR-TO-EMITTER VOLTAGE:			
With dc emitter-to-base volts = -1. . . . .	-15 max.	volts	
EMITTER-TO-BASE VOLTAGE . . . . .	-10 max.	volts	
COLLECTOR CURRENT . . . . .	-100 max.	ma	
EMITTER CURRENT . . . . .	100 max.	ma	
TRANSISTOR DISSIPATION: <sup>a</sup>			
At ambient temperature of 25° C or below. . . . .	120 max.	mw	
At ambient temperature of 55° C . . . . .	35 max.	mw	
At ambient temperature of 71° C . . . . .	10 max.	mw	
AMBIENT-TEMPERATURE RANGE:			
Operating and storage . . . . .	-65 to +85	°C	
LEAD TEMPERATURE:			
For 10 seconds maximum. . . . .	255 max.	°C	

### ELECTRICAL CHARACTERISTICS and OPERATING CONSIDERATIONS

shown under Type 2N581 also apply to the 2N583

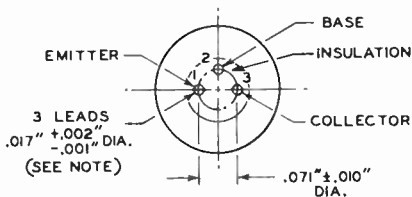
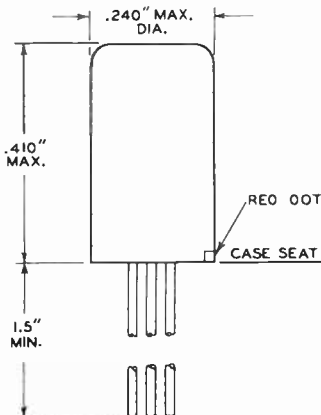
<sup>a</sup> See accompanying *Rating Chart* and also *Transistor-Dissipation Rating Chart* in General Section.

← Indicates a change.



# 2N583

JEDEC No. T0-1

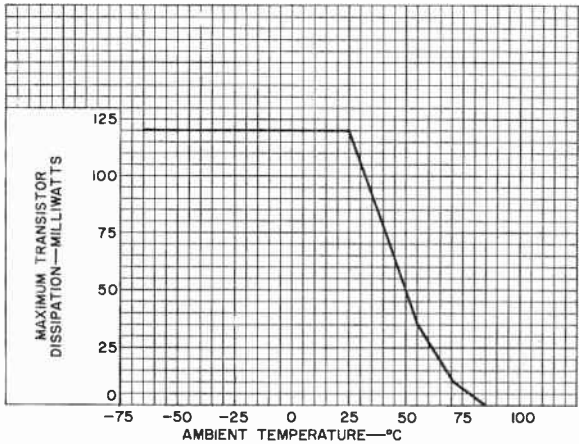


92CS-9148R6

NOTE: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE CASE SEAT. BETWEEN 0.25" AND 1.5", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.



## RATING CHART



92CS-10908RI





## Transistor

GERMANIUM P-N-P ALLOY-JUNCTION TYPE  
For Computer Switching Applications

### GENERAL DATA

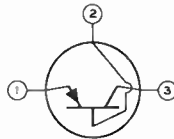
#### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.410"
Maximum Diameter . . . . .	0.240"
Dimensional Outline . . . . .	JEDEC No. TO-1
Case . . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>

Terminal Diagram:

BOTTOM VIEW

Lead 1 - Emitter  
  
Lead 2 - Base



Lead 3 - Collector  
(Adjacent to red dot on side of case)

### SWITCHING SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values*:

COLLECTOR-TO-BASE VOLTAGE . . . . .	-25 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE: With dc emitter-to-base volts = -1 . . . . .	-14 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-12 max.	volts
COLLECTOR CURRENT . . . . .	-100 max.	ma
EMITTER CURRENT . . . . .	100 max.	ma
TRANSISTOR DISSIPATION: <sup>a</sup>		
At ambient temperature of 25° C or below . . . . .	120 max.	mw
At ambient temperature of 55° C . . . . .	35 max.	mw
At ambient temperature of 71° C . . . . .	10 max.	mw
AMBIENT-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +85	°C
LEAD TEMPERATURE:		
For 10 seconds maximum . . . . .	255 max.	°C

### ELECTRICAL CHARACTERISTICS and OPERATING CONSIDERATIONS

shown under Type 2N582 also apply to the 2N584

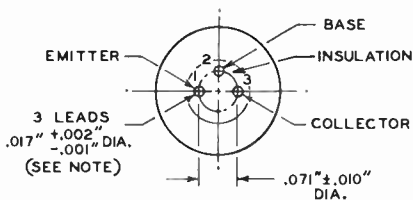
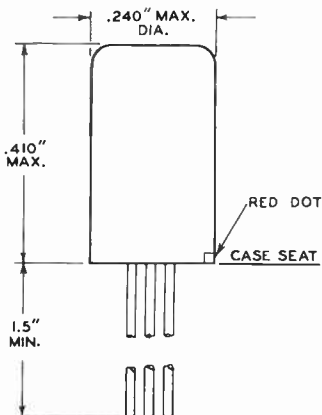
<sup>a</sup> See accompanying *Rating Chart* and also *Transistor-Dissipation Rating Chart* in General Section.

← Indicates a change.



# 2N584

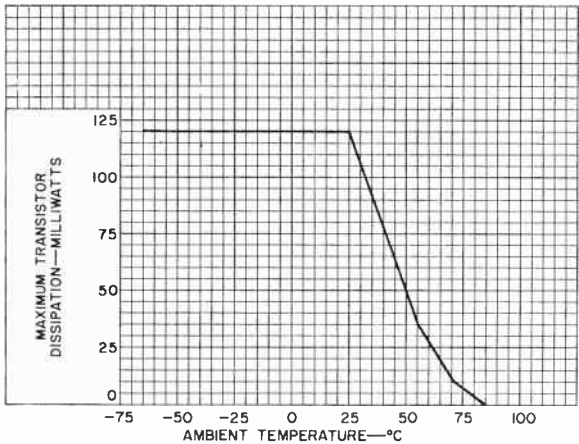
JEDEC No. TO-1



92CS-9148R6

NOTE: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE CASE SEAT. BETWEEN 0.25" AND 1.5", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

## RATING CHART



92CS-10908RI





## Power Transistor

## SILICON N-P-N DIFFUSED-JUNCTION TYPE

For Medium-Power Switching and Amplifier Service in Industrial and Military Applications

The 2N656 is the same as the 2N497 except for the following item:

## ELECTRICAL CHARACTERISTICS

	Min.	Typical	Max.
DC Current Transfer Ratio for dc collector-to-emitter volts = 10, dc collector ma. = 200 . . . . . $h_{FE}$	30	-	90







## Transistor

## SILICON N-P-N DOUBLE-DIFFUSED-JUNCTION TYPE

For Switching Service in Commercial  
and Military Data-Processing Systems

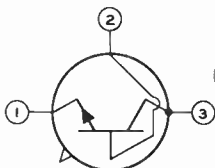
## GENERAL DATA

## Mechanical:

Operating Position. . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter. . . . .	0.370"
Dimensional Outline . . . . .	JEDEC No. TO-5
Case. . . . .	Welded, Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length. . . . .	1.5"
Orientation and diameter. . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base

Lead 3 - Collector,  
Case

## SWITCHING SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values*:

COLLECTOR-TO-BASE VOLTAGE with emitter open. . . . .	60 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With external base-to-emitter resistor		
(ohms) $\leq 10$ . . . . .	40 max.	volts
EMITTER-TO-BASE VOLTAGE with collector open. . . . .	5 max.	volts
COLLECTOR CURRENT . . . . .	500 max.	ma
TRANSISTOR DISSIPATION: <sup>a</sup>		
At case temperature <sup>b</sup> of 25° C or below. . . . .	2 max.	watts
At free-air temperature of 25° C or below . . . . .	0.6 max.	watt
OPERATING TEMPERATURE RANGE:		
Case <sup>b</sup> or free air . . . . .	-65 to +175	°C
LEAD TEMPERATURE: <sup>c</sup>		
For 10 seconds maximum. . . . .	255 max.	°C

<sup>a</sup> See accompanying *Rating Chart*.<sup>b</sup> Measured at center of seating surface.<sup>c</sup> Measured 1/16"  $\pm$  1/32" down from seating surface.

# 2N696

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and free-air temperature of 25° C unless otherwise specified

Min. Typical Max.

DC Collector Breakdown						
Voltage for dc collector ma. = 0.1, emitter open. . . . .	$BV_{CBO}$	60	75	-	volts	
DC Collector-to-Emitter						
Voltage for dc collector ma. = 100 <sup>d</sup> , external base-to-emitter resistor (ohms) = 10. . . . .	$V_{CER}$	40	50	-	volts	
DC Emitter Breakdown Voltage						
for dc emitter ma. = 0.1, collector open . . . . .	$BV_{EBO}$	5	7.5	-	volts	
DC Base-to-Emitter Saturation Voltage for dc collector ma. = 150, dc base ma. = 15 . . . . .						
	$V_{BE(sat)}$	-	1	1.3	volts	
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = 150, dc base ma. = 15 . . . . .						
	$V_{CE(sat)}$	-	0.9	1.5	volts	
DC Collector Cutoff Current						
for dc collector volts = 30, dc emitter ma. = 0, free-air temperature = 25° C. . . . .	$I_{CBO}$	-	0.01	1	$\mu a$	
150° C. . . . .		-	1	100	$\mu a$	
Collector-to-Base Capacitance for dc collector volts = 10, dc emitter ma. = 0. . . . .						
	$C_{ob}$	-	20	35	$\mu\mu f$	
DC-Pulse Forward-Current Transfer Ratio for dc collector-to-emitter volts = 10, dc collector ma. = 150, pulse duration (msec) $\leq$ 12, duty factor $\leq$ 0.02 . . . . .						
	$h_{FE}$	20	40	60		
Small-Signal Forward-Current Transfer Ratio for dc collector-to-emitter volts = 10, dc collector ma. = 50, frequency of 20 Mc. . . . .						
	$h_{fe}$	2	4	-	Mc	
Gain-Bandwidth Product. . . . .						
	$f_T$	-	80	-	Mc	

<sup>d</sup> Pulsed to prevent excessive heating of collector junction.

<sup>e</sup> Frequency at which small-signal forward current transfer ratio is equal to 1.

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

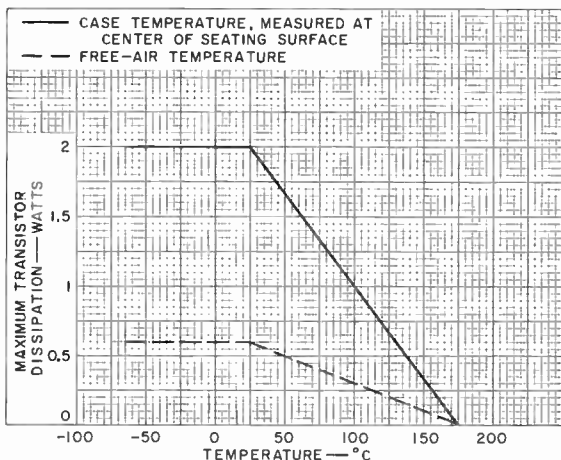


The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the seals of the leads and damage the transistor.

It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.

This transistor is intended for use in socketed, single-side printed-circuit boards and in conventional wire-in-type circuits. If this transistor is used in double-side printed-circuit boards or in printed-circuit boards utilizing eyelets, it may be necessary to use an insulating washer or similar standoff device made of good dielectric material to prevent the solder from shorting the leads to each other or to the boards, and to prevent the collector from shorting to ground.

### RATING CHART

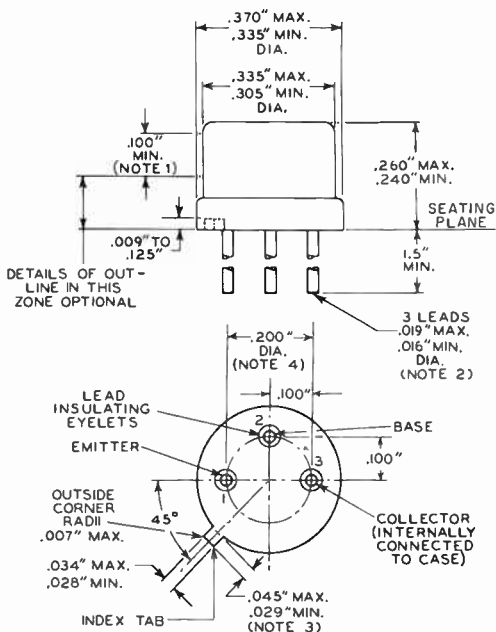


92CS-11161R1



# 2N696

JEDEC No. T0-5



92CS-10429R2

**NOTE 1:** THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE VARIATION IN ACTUAL DIAMETER WITHIN THE ZONE SHALL NOT EXCEED 0.010".

**NOTE 2:** THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE SEATING PLANE. BETWEEN 0.25" AND 1.5" A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

**NOTE 3:** MEASURED FROM MAXIMUM DIAMETER OF THE ACTUAL DEVICE.

**NOTE 4:** LEADS HAVING MAXIMUM DIAMETER (0.019") MEASURED IN GAUGING PLANE 0.054" ± 0.001" - 0.000" BELOW THE SEATING PLANE OF THE DEVICE SHALL BE WITHIN 0.007" OF THEIR TRUE LOCATIONS RELATIVE TO A MAXIMUM-WIDTH TAB.



## Transistor

## SILICON N-P-N DOUBLE-DIFFUSED-JUNCTION TYPE

For Switching Service in Commercial  
and Military Data-Processing Systems

The 2N697 is the same as the 2N696 except for the following items:

## ELECTRICAL CHARACTERISTICS

	Min.	Typical	Max.	
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = 150, dc base ma. = 15. . . $V_{CE(sat)}$	-	0.8	1.5	volts
DC-Pulse Forward-Current Transfer Ratio for dc collector-to-emitter volts = 10, dc collector ma. = 150, pulse duration (msec) $\leq 12$ , duty factor $\leq 0.02$ . . . $h_{FE}$	40	75	120	
Small-Signal Forward Current Transfer Ratio for dc collector-to-emitter volts = 10, dc collector ma. = 150, frequency of 20 Mc. . . $h_{fe}$	2.5	5	-	
Gain Bandwidth Product <sup>e</sup> . $f_T$	-	100	-	Mc

<sup>e</sup> Frequency at which small-signal forward current transfer ratio is equal to 1.





## Mesa Transistor

### GERMANIUM P-N-P DIFFUSED-BASE TYPE

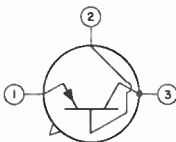
For Logic-Circuit Applications in Commercial and Military Data-Processing Equipment

#### GENERAL DATA

##### Mechanical:

Operating Position. . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.210"
Maximum Diameter. . . . .	0.230"
Dimensional Outline . . . . .	JEDEC No. TO-18
Case. . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length. . . . .	0.500"
Orientation and diameter. . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector,  
Case

#### SWITCHING SERVICE

##### Maximum and Minimum Ratings, *Absolute-Maximum Values:*

COLLECTOR-TO-BASE VOLTAGE. . . . .	-15 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE . . . . .	-15 max.	volts
EMITTER-TO-BASE VOLTAGE. . . . .	-3.5 max.	volts
COLLECTOR CURRENT. . . . .	-50 max.	ma
EMITTER CURRENT. . . . .	50 max.	ma

##### TRANSISTOR DISSIPATION:

Operation in free air (See *Rating Chart*):

At ambient temperature of 25° C. . . . .	150 max.	mw
At ambient temperature of 55° C. . . . .	90 max.	mw
At ambient temperature of 71° C. . . . .	58 max.	mw

Operation with heat sink:

At case temperature of 25° C <sup>a</sup> . . . . .	300 max.	mw
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##### AMBIENT-TEMPERATURE RANGE:

Operating and storage. . . . .	-65 to +100	°C
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##### LEAD TEMPERATURE:

For immersion in molten solder for 10 seconds maximum . . . . .	230 max.	°C
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<sup>a</sup> For case temperatures above 25° C, reduce the dissipation by 4 milliwatts/°C.



# 2N705

## ELECTRICAL CHARACTERISTICS

*Voltage values are given with respect to base unless otherwise specified. Ambient temperature of 25° C.*

		Min.	Typical	Max.	
DC Collector Breakdown Voltage for dc collector ma. = -0.1, emitter current = 0 . . . . .	$BV_{CBO}$	-15	-	-	volts
DC Emitter Breakdown Voltage for dc emitter ma. = -0.1, collector current = 0 . . . . .	$BV_{EBO}$	-3.5	-	-	volts
DC Collector-to-Emitter Breakdown Voltage for dc emitter volts = 0, dc collector ma. = -0.1 . . . . .	$BV_{CES}$	-15	-	-	volts
DC Base-to-Emitter Voltage for dc collector ma. = -10, dc base ma. = -0.4 . . . . .	$V_{BE}$	-0.34	-	-0.44	volt
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = -10, dc base ma. = -0.4 . . . . .	$V_{CE(sat)}$	-	-	-0.3	volt
DC Collector-Cutoff Current for dc collector volts = -5, emitter current = 0 . . . . .	$I_{CBO}$	-	-	-3	$\mu\text{a}$
Small-Signal Current Transfer Ratio for dc collector-to-emitter volts = -5, dc collector ma. = -10, frequency (Mc) = 100 . . . . .	$h_{fe}$	-	3	-	
DC Current Transfer Ratio for dc collector-to-emitter volts = -0.3, dc collector ma. = -10 . . . . .	$h_{FE}$	25	-	-	
Collector Transition Capacitance for dc collector volts = -10, emitter current = 0, frequency (Mc) = 1 . . . . .	$C_{TC}$	-	5	-	$\mu\text{f}$
Emitter Transition Capacitance for dc emitter volts = -2, collector current = 0, frequency (Mc) = 1 . . . . .	$C_{TE}$	-	3.5	-	$\mu\text{f}$





"Turn-On" Time (Delay time + rise time) for dc collector-to-emitter supply volts = -3.5, "turn-on" base ma. = -1, collector resistor (ohms) = 300, dc "off" base-to-emitter volts = 0.5. . . . .	$t_d + t_r$	-	-	75	$\mu\text{sec}$
Storage Time for dc collector-to-emitter supply volts = -3.5, "turn-on" base ma. = -1, "turn-off" base ma. = 0.25, collector resistor (ohms) = 300. . .	$t_s$	-	-	100	$\mu\text{sec}$
Fall Time for dc collector-to-emitter supply volts = -3.5, "turn-on" base ma. = -1, "turn-off" base ma. = 0.25, collector resistor (ohms) = 300 . . . . .	$t_f$	-	-	100	$\mu\text{sec}$

### PERFORMANCE TESTS

This transistor type is tested in accordance with Military Specification MIL-S-19500B.

### OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.

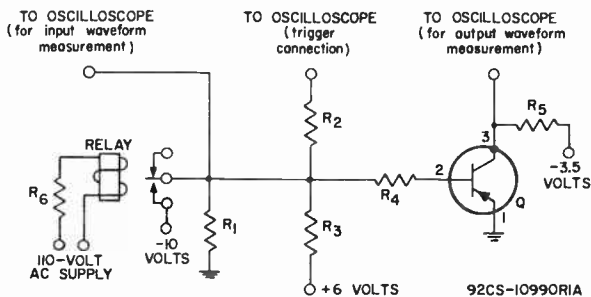
This transistor is intended for use in single-side printed-circuit boards and in conventional wire-in-type circuits. If this transistor is used in double-side printed-circuit boards or in printed-circuit boards utilizing eyelets, it may be necessary to use an insulating washer or similar standoff device made of good dielectric material to prevent the solder from shorting the leads to each other or to the board, and to prevent the collector from shorting to ground.

It is to be noted that the case of this transistor operates at the collector voltage. Consideration, therefore, should be given to the possibility of shock hazard, if the case of this transistor is to operate at a voltage appreciably above or below ground potential. In such cases, suitable precautionary measures should be taken.

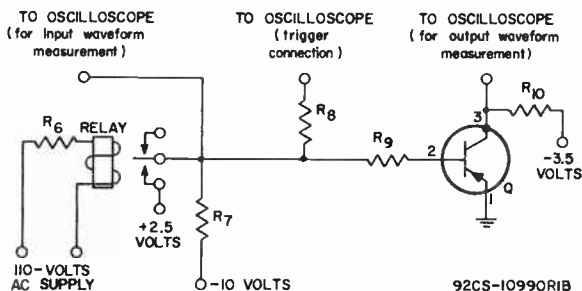


# 2N705

## SWITCHING-TIME TEST CIRCUITS



(a) "Turn-On" Time Measurement Circuit



(b) "Turn-Off" Time Measurement Circuit

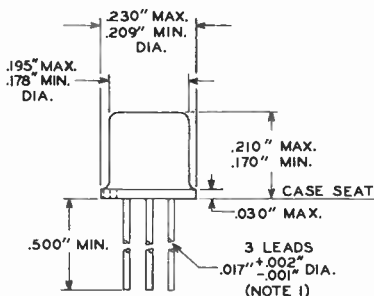
Q: Transistor type 2N705	$R_6$ : 7500 ohms, 0.1 watt
$R_1$ : 1000 ohms, 0.5 watt	$R_7$ : 200 ohms, 0.1 watt
$R_2$ : 5100 ohms, 0.5 watt	$R_8$ : 5100 ohms, 0.5 watt
$R_3$ : 11,000 ohms, 0.5 watt	$R_9$ : 10,000 ohms, 0.5 watt
$R_4$ : 10,000 ohms, 0.5 watt	$R_{10}$ : 300 ohms, 0.5 watt
$R_5$ : 300 ohms, 0.5 watt	

Relay: C.P. Clare mercury relay model HG-2A-1004,  
or equivalent

Oscilloscope: Tektronix model 545, or equivalent

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JEDEC No. T0-18



92CS-10605RI

NOTE 1: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE CASE SEAT. BETWEEN 0.25" TO THE END OF THE LEAD A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

NOTE 2: MAXIMUM DIAMETER LEADS AT A GAUGING PLANE 0.054"  $\pm$  0.001" - 0.000" BELOW CASE SEAT TO BE WITHIN 0.007" OF THEIR TRUE LOCATION RELATIVE TO MAXIMUM WIDTH TAB AND TO THE MAXIMUM 0.230" DIAMETER MEASURED WITH A SUITABLE GAUGE. WHEN GAUGE IS USED, MEASUREMENT WILL BE MADE AT CASE SEAT.

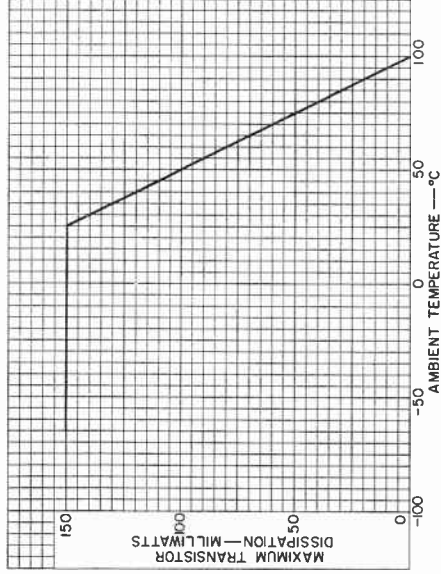
NOTE 3: FOR VISUAL ORIENTATION ONLY.

NOTE 4: TAB LENGTH TO BE 0.028" MINIMUM AND 0.048" MAXIMUM, AND WILL BE DETERMINED BY SUBTRACTING DIAMETER "A" FROM DIMENSION "B".



# 2N705

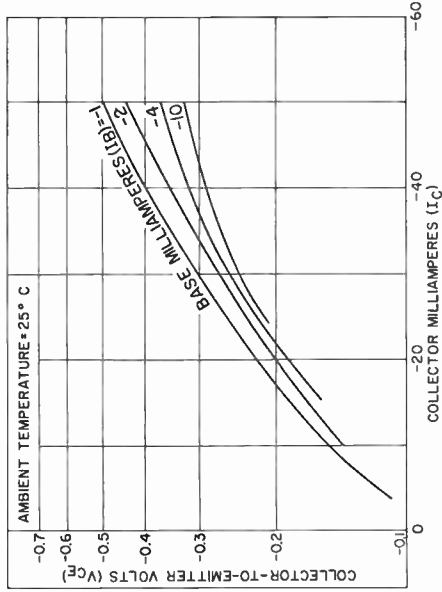
## RATING CHART



92CS-10968

World Precision Instrument

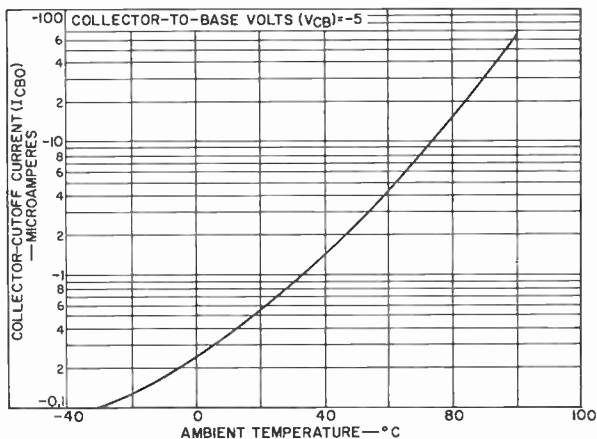
## TYPICAL COLLECTOR CHARACTERISTICS



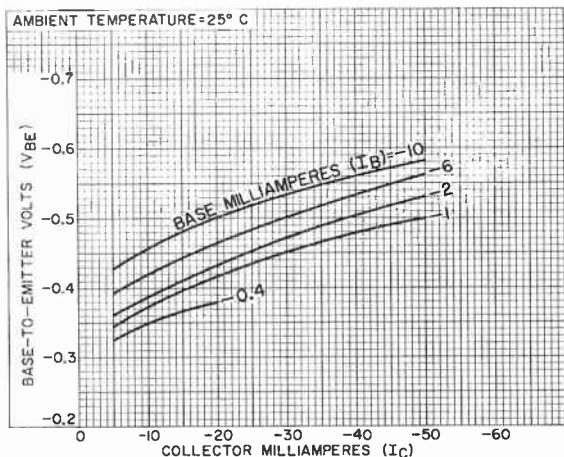
92CS-10971



## TYPICAL CHARACTERISTICS



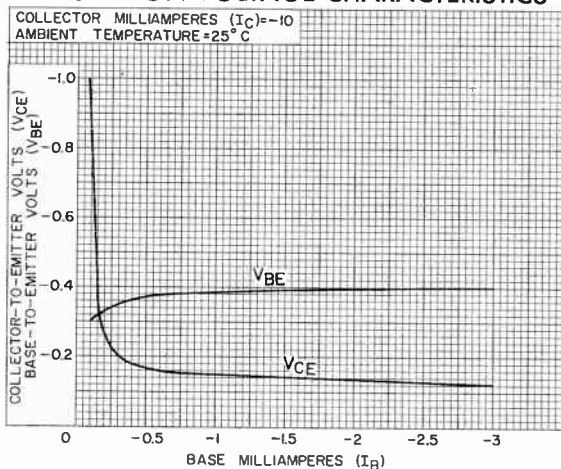
92CS-10976



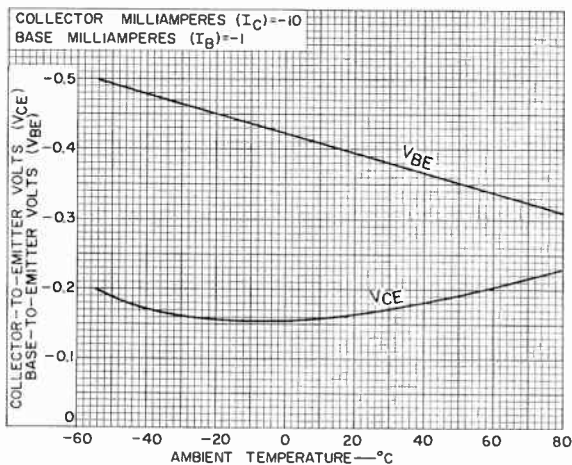
92CS-10969



## TYPICAL SATURATION-VOLTAGE CHARACTERISTICS

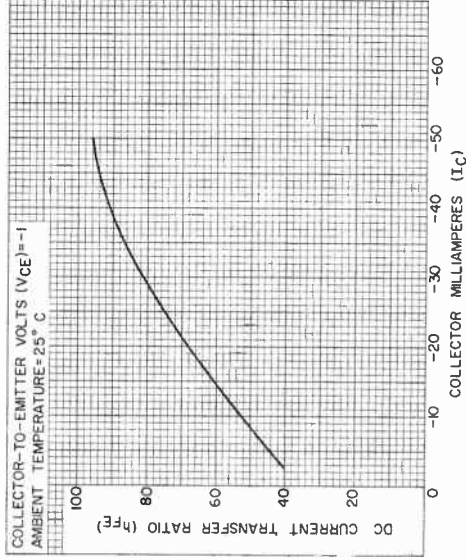


92CS-10972



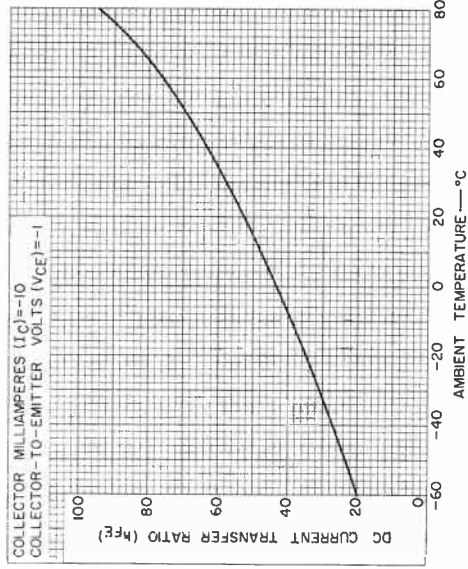
92CS-10986

## TYPICAL DC-CURRENT-TRANSFER-RATIO CHARACTERISTICS



World Radio History

92CS-10974

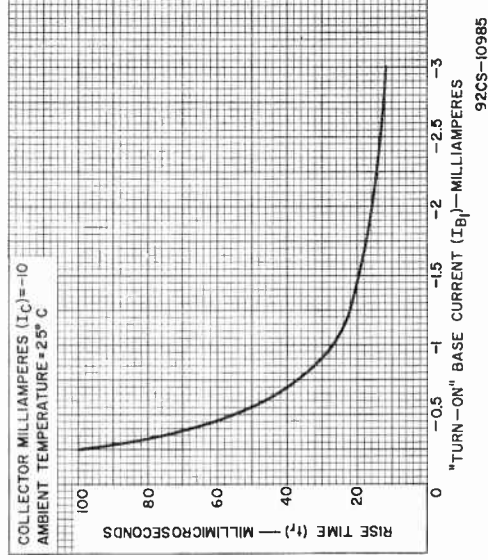
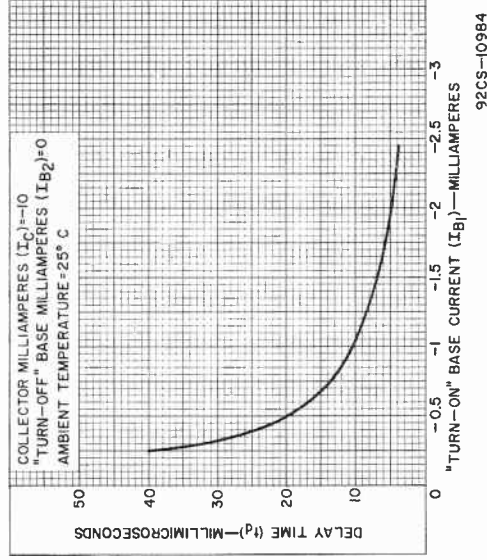


92CS-10988



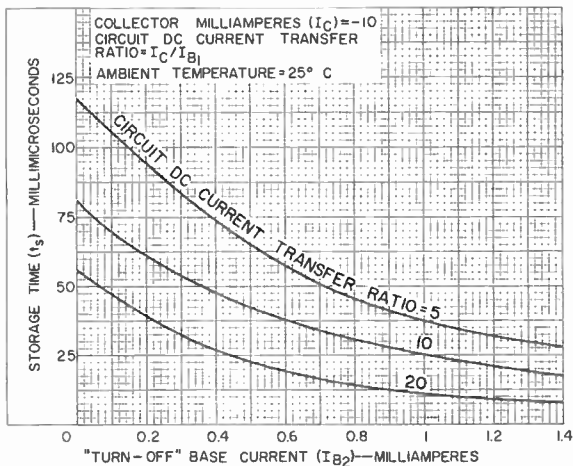
# 2N705

## TYPICAL CHARACTERISTICS

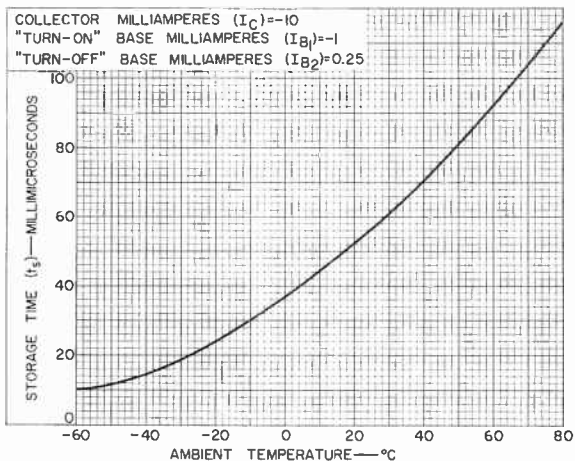




## TYPICAL STORAGE-TIME CHARACTERISTICS



92CS-10975

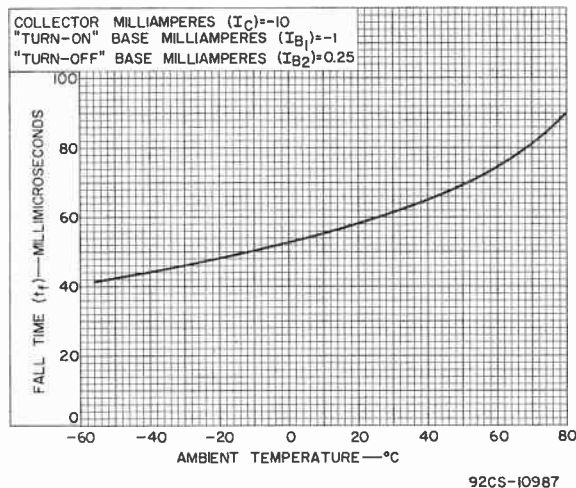
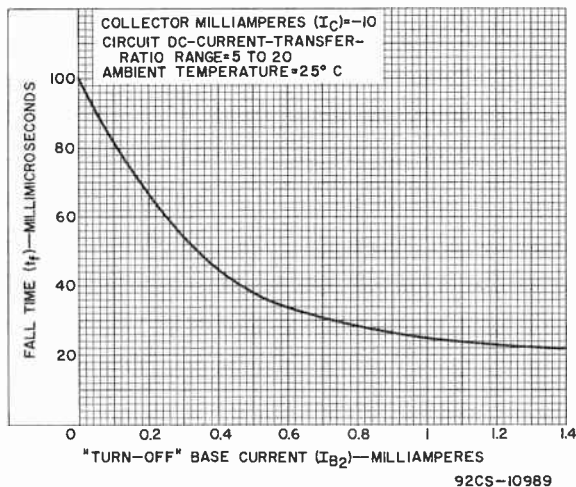


92CS-10973



# 2N705

## TYPICAL FALL-TIME CHARACTERISTICS



## Mesa Transistor

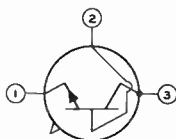
SILICON N-P-N DIFFUSED-JUNCTION TYPE  
For Switching Applications

## GENERAL DATA

## Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.210"
Maximum Diameter . . . . .	0.230"
Dimensional Outline . . . . .	JEDEC No. TO-18
Case . . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	0.500"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector,  
Case

## SWITCHING SERVICE

## Maximum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	25 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With external resistor (ohms) = 10		
between base and emitter . . . . .	20 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	3 max.	volts
TRANSISTOR DISSIPATION (See <i>Rating Chart</i> ):		
Operation in free air:		
At ambient temperature of 25° C . . . . .	0.3 max.	watt
Operation with heat sink:		
At case temperature of 25° C . . . . .	1 max.	watt
At case temperature of 100° C . . . . .	0.5 max.	watt
JUNCTION TEMPERATURE . . . . .	175 max.	°C

## ELECTRICAL CHARACTERISTICS

*Voltage values are given with respect to base and ambient temperature of 25° C unless otherwise specified*

*Min. Typical Max.*

DC Base-to-Emitter Saturation Voltage for dc collector ma. = 10, dc base ma. = 1 . . . . .

$V_{BE}$ (sat)	-	0.75	0.9	volt
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# 2N706

DC Collector-to-Emitter Saturation Voltage for dc collector ma. = 10, dc base ma. = 1 . . . . .	$V_{CE}$	-	0.3	0.6	volt
DC Collector-Cutoff Current for dc collector volts = 15, emitter open, ambient temperature = 25° C . . . . .	$I_{CBO}$	-	0.005	0.5	$\mu\text{a}$
150° C . . . . .		-	3.5	30	$\mu\text{a}$
Collector-to-Base Capacitance for dc collector volts = 10, emitter open.	$C_{ob}$	-	5	6	$\mu\text{m}f$
DC-Pulse Current Transfer Ratio for dc collector-to-emitter volts = 1, dc collector ma. = 10, pulse duration (msec) $\leq 12$ , duty factor $\leq 0.02$ .	$h_{FE}$	20	-	-	
Small-Signal Current Transfer Ratio for dc collector-to-emitter volts = 15, dc collector ma. = 10, frequency of 100 Mc. . . . .	$h_{fe}$	2	4	-	
Gain-Bandwidth Product . . . . .	GBW	-	400	-	Mc
Storage Time for dc collector ma. = 10, "turn-on" base ma. ( $I_{B1}$ ) = 10, "turn-off" base ma. ( $I_{B2}$ ) = -10 . . . . .	$t_s$	-	16	60	$\text{m}\mu\text{sec}$

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using this transistor, the temperature of the solder should not exceed 255° C for a maximum immersion period of 10 seconds.

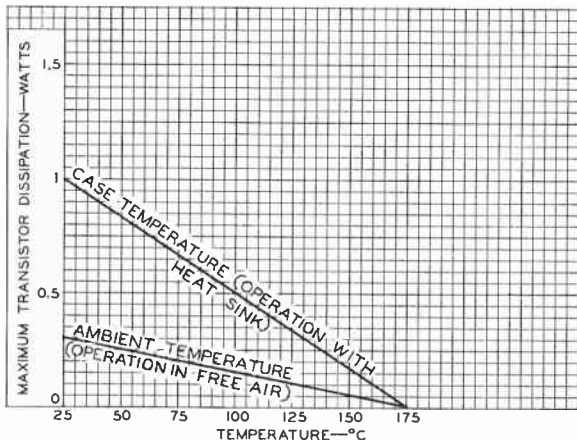
This transistor is intended for use in single-side printed-circuit boards and in conventional wire-in-type circuits. If this transistor is used in double-side printed-circuit boards or in printed-circuit boards utilizing eyelets, it may be necessary to use as insulating washer or similar standoff device made of good dielectric material to prevent the solder



from shorting the leads to each other or to the board, and to prevent the collector from shorting to ground.

It is to be noted that the case of this transistor operates at the collector voltage. Consideration, therefore, should be given to the possibility of shock hazard, if the case of this transistor is to operate at a voltage appreciably above or below ground potential. In such cases, suitable precautionary measures should be taken.

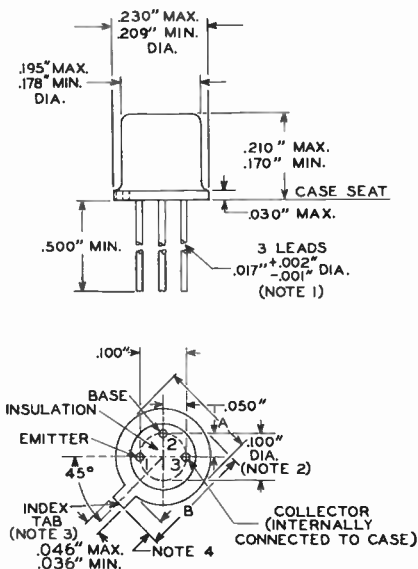
## RATING CHART



92CS-10602



# 2N706



92CS-10605RI

NOTE 1: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN  $0.05''$  AND  $0.25''$  FROM THE CASE SEAT. BETWEEN  $0.25''$  TO THE END OF THE LEAD A MAXIMUM DIAMETER OF  $0.021''$  IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

NOTE 2: MAXIMUM DIAMETER LEADS AT A GAUGING PLANE  $0.054'' + 0.001'' - 0.000''$  BELOW CASE SEAT TO BE WITHIN  $0.007''$  OF THEIR TRUE LOCATION RELATIVE TO MAXIMUM WIDTH TAB AND TO THE MAXIMUM  $0.230''$  DIAMETER MEASURED WITH A SUITABLE GAUGE. WHEN GAUGE IS USED, MEASUREMENT WILL BE MADE AT CASE SEAT.

NOTE 3: FOR VISUAL ORIENTATION ONLY.

NOTE 4: TAB LENGTH TO BE  $0.028''$  MINIMUM AND  $0.048''$  MAXIMUM, AND WILL BE DETERMINED BY SUBTRACTING DIAMETER "A" FROM DIMENSION "B".

## Mesa Transistor

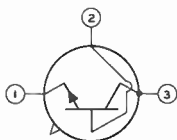
SILICON N-P-N DIFFUSED-JUNCTION TYPE  
For Switching Applications

### GENERAL DATA

#### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.210"
Maximum Diameter . . . . .	0.230"
Dimensional Outline . . . . .	JEDEC No. TO-18
Case . . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	0.500"
Orientation and diameter . . . . .	See Dimensional Outline
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector,  
Case

### SWITCHING SERVICE

Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	25 max.	volts
COLLECTOR TO EMITTER VOLTAGE:		
With external resistor (ohms) = 10		
between base and emitter . . . . .	20 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	5 max.	volts
COLLECTOR DISSIPATION:		
Operation in free air:		
At ambient temperature of 25° C . . . . .	0.3 max.	watt
Operation with heat sink:		
At case temperature of 100° C . . . . .	1 max.	watt
JUNCTION TEMPERATURE . . . . .	175 max.	°C
AMBIENT-TEMPERATURE RANGE:		
Storage . . . . .	-65 to +175	°C

### ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and ambient temperature of 25° C unless otherwise specified  
Min. Typical Max.

DC Base-to-Emitter Saturation Voltage for dc collector ma. = 10, dc base ma. = 1 . . . . .

$V_{BE}$ (sat)	0.7	-	0.9	volt
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# 2N706-A

DC Collector-to-Emitter Saturation Voltage for dc collector ma. = 10, dc base ma. = 1 . . . . .	$V_{CE}$	-	-	0.6	volt
DC Collector-Cutoff Current for dc collector volts = 15, emitter open, ambient temperature = 25° C . . . . .	$i_{CBO}$	-	-	0.5	$\mu a$
150° C . . . . .		-	-	30	$\mu a$
DC Current Transfer Ratio for collector-to-emitter volts = 1, dc collector ma. = 10 . . . . .	$h_{FE}$	20	-	60	
Small-Signal Current Transfer Ratio for dc collector-to-emitter volts = 10, dc collector ma. = 10, frequency of 100 Mc . . . . .	$h_{fe}$	2	-	-	
"Turn-On" Time for dc collector supply volts = 3, "turn-on" base ma. ( $I_{B1}$ ) = 3, "turn-off" base ma. ( $I_{B2}$ ) = -1 . . . . .		-	-	40	$m\mu sec$
"Turn-Off" Time for dc collector supply volts = 3, "turn-on" base ma. ( $I_{B1}$ ) = 3, "turn-off" base ma. ( $I_{B2}$ ) = -1 . . . . .		-	-	75	$m\mu sec$
Storage Time for dc collector ma. = 10, "turn-on" base ma. ( $I_{B1}$ ) = 10, "turn-off" base ma. ( $I_{B2}$ ) = 10 . . . . .	$t_s$	-	-	25	$m\mu sec$

OPERATING CONSIDERATIONS  
and DIMENSIONAL OUTLINE  
shown under Type 2N706 also apply to the 2N706-A





## Transistor

### SILICON N-P-N DOUBLE-DIFFUSED-JUNCTION PLANAR TYPE

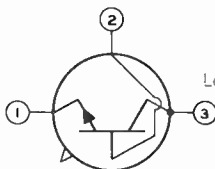
For Switching and Amplifier Applications  
in Industrial and Military Equipment

#### GENERAL DATA

##### Mechanical:

Operating Position. . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.210"
Maximum Diameter. . . . .	0.230"
Dimensional Outline . . . . .	JEDEC No. TO-18
Case. . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length. . . . .	0.500"
Orientation and diameter. . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector,  
Case

#### SWITCHING SERVICE

##### Maximum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE:		
With emitter open . . . . .	40 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With external resistor (ohms) $\leq 10$ between base and emitter. . . . .	20 max.	volts
With base open. . . . .	15 max.	volts
EMITTER-TO-BASE VOLTAGE:		
With collector open . . . . .	5 max.	volts
TRANSISTOR DISSIPATION: <sup>a</sup>		
At case temperature <sup>b</sup> of 25° C or below. . . . .	1.2 max.	watts
At case temperature <sup>b</sup> of 100° C. . . . .	0.68 max.	watt
At free-air temperature of 25° C or below. . . . .	0.36 max.	watt
TEMPERATURE RANGE:		
Storage . . . . .	-65 to +300	°C
Operating (Junction). . . . .	200 max.	°C
LEAD TEMPERATURE: <sup>c</sup>		
For 10 seconds maximum. . . . .	300 max.	°C

<sup>a</sup> See accompanying Rating Chart.

<sup>b</sup> Measured at center of seating plane.

<sup>c</sup> Measured 1/16"  $\pm$  1/32" down from seating plane.



# 2N708

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and free-air temperature of 25° C unless otherwise specified.

		Min.	Max.	
DC Collector Breakdown Voltage for dc collector ma. = 0.001, emitter ma. = 0 . . . . .	$BV_{CBO}$	40	-	volts
DC Emitter Breakdown Voltage for dc emitter ma. = 0.1, collector ma. = 0 . . . . .	$BV_{EBO}$	5	-	volts
DC Collector-to-Emitter Sustaining Voltage: With dc collector pulsed ma. = 30, external base- to-emitter resistor (ohms) $\leq 10$ . . . . .	$V_{CER}^{(sus)}$	20	-	volts
With dc collector pulsed ma. = 30, base open. . . . .	$V_{CEO}^{(sus)}$	15	-	volts
DC Base-to-Emitter Saturation Voltage: With dc collector ma. = 10, dc base ma. = 1, free- air temperature = 25° C . . . . .	$V_{BE}^{(sat)}$	0.72	0.8	volt
With dc collector ma. = 7, dc base ma. = 0.7, free- air temperature = -55° C . . . . .		-	0.9	volt
DC Collector-to-Emitter Saturation Voltage: With dc collector ma. = 10, dc base ma. = 1, free- air temperature = 25° C . . . . .	$V_{CE}^{(sat)}$	-	0.4	volt
With dc collector ma. = 7, dc base ma. = 0.7, free- air temperature range = -55 to +125° C . . . . .		-	0.4	volt
DC Collector-Cutoff Current for dc collector volts = 20, dc emitter ma. = 0, free-air temperature = 25° C . . . . .	$I_{CBO}$	-	0.025	$\mu a$
150° C . . . . .		-	15	$\mu a$
DC Collector Current for base-to-emitter forward bias volts = 0.25, dc collector volts = 20, free- air temperature = 125° C . . . . .	$I_{CEX}$	-	10	$\mu a$
DC Emitter-Cutoff Current for dc base-to-emitter volts = 4, dc collector ma. = 0 . . . . .	$I_{EBO}$	-	0.08	$\mu a$



Base-Spreading Resistance <sup>d</sup> for dc collector-to-emitter volts = 10, dc collector ma. = 10, frequency (Mc) = 300 . . . . .	$r_{b'}$	-	50	ohms
Collector-to-Base Capacitance for dc collector volts = 10, dc emitter ma. = 0 . . . . .	$C_{ob}$	-	6	$\mu\text{mf}$
Small-Signal Current Transfer Ratio for dc collector-to-emitter volts = 10, dc collector ma. = 10, frequency (Mc) = 100 . . . . .	$h_{fe}$	3	-	
DC Current Transfer Ratio: With dc collector-to-emitter volts = 1, free-air temperature = 25° C, dc collector ma. =	$h_{FE}$			
10 . . . . .		30	120	
0.5 . . . . .		15	-	
With dc collector-to-emitter volts = 1, dc collector ma. = 10, free-air temperature = -55° C . . . . .		15	-	
Storage Time <sup>e</sup> for dc collector supply volts = 10, collector resistor (ohms) = 1000, "turn-on" and "turn-off" base ma. = 10 each, dc collector ma. = 10 . . . . .	$t_s$	-	25	$\mu\text{sec}$
Thermal Resistance:	$R_T$			
Junction-to-case . . . . .		-	145	°C/watt
Junction-to-free air . . . . .		-	480	°C/watt

<sup>d</sup> Base-Spreading Resistance ( $r_{b'}$ ) is the product of  $R_e$  and  $h_{ie}$  (small-signal value of the short-circuit input impedance).

<sup>e</sup> See accompanying Storage-Time-Measurement Circuit.

### OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

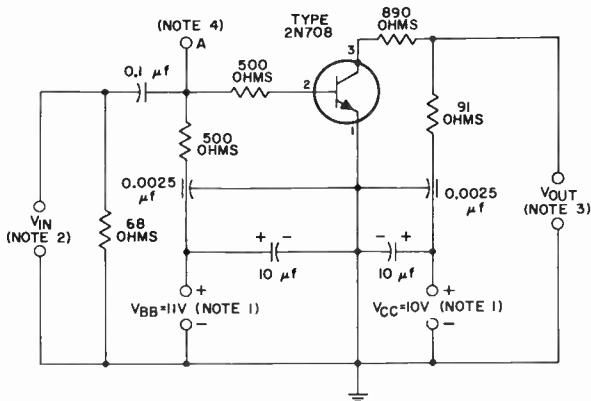
The flexible leads of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the seating plane provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.

It is to be noted that the case of this transistor operates at the collector voltage. Consideration, therefore, should be given to the possibility of shock hazard, if the case of this transistor is to operate at a voltage appreciably above or below ground potential. In such cases, suitable precautionary measures should be taken.



# 2N708

## STORAGE-TIME-MEASUREMENT CIRCUIT



92CS-11228

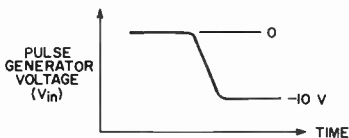
**NOTE 1:** WITH CERTAIN TYPES OF POWER SUPPLIES, IT MAY BE NECESSARY TO CONNECT 25- $\mu$ f DECOUPLING CAPACITORS ACROSS THE POWER-SUPPLY TERMINALS FOR  $V_{CC}$  AND  $V_{BB}$ .

**NOTE 2:** INPUT VOLTAGE ( $V_{IN}$ ) OBTAINED FROM MERCURY-RELAY TYPE PULSE GENERATOR HAVING AN OUTPUT IMPEDANCE OF 50 OHMS.

**NOTE 3:** THE ASSOCIATED INPUT AND OUTPUT WAVEFORMS SHOWN SHOULD BE MONITORED BY MEANS OF A SAMPLING OSCILLOSCOPE HAVING AN INPUT IMPEDANCE OF 50 OHMS.

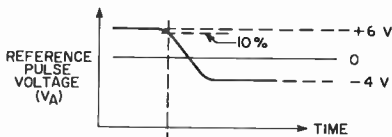
**NOTE 4:** TEST POINT FOR OBSERVATION OF REFERENCE PULSE VOLTAGE ( $V_A$ ).

### ASSOCIATED WAVE FORMS

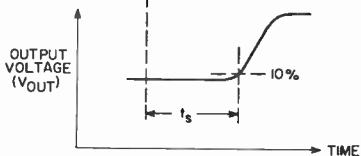


RISE TIME  $< 1\text{m}\mu\text{SEC}$   
 PULSE DURATION  $\geq 300\text{m}\mu\text{SEC}$   
 DUTY FACTOR  $< 0.02$

*INPUT WAVE FORM*



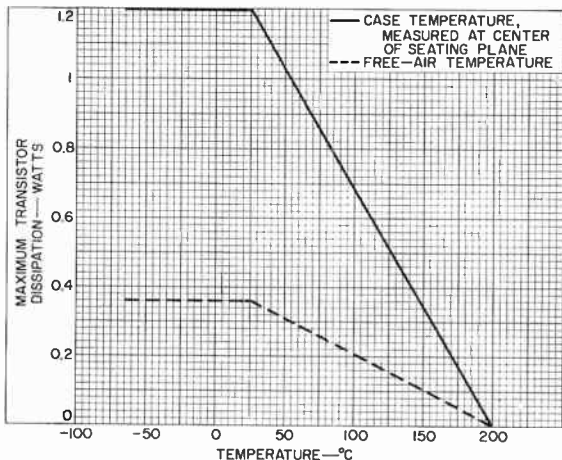
REFERENCE WAVE FORM OBSERVED AT POINT "A" IN STORAGE-TIME-MEASUREMENT CIRCUIT



OUTPUT WAVE FORM

92CS-11224

## RATING CHART

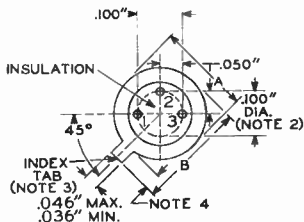
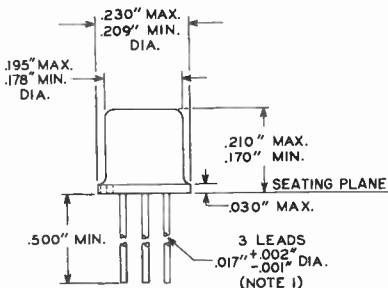


92CS-11231



# 2N708

JEDEC No. T0-18



92CS-10605R1

NOTE 1: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN  $0.05''$  AND  $0.25''$  FROM THE SEATING PLANE. BETWEEN  $0.25''$  TO THE END OF THE LEAD, A MAXIMUM DIAMETER OF  $0.021''$  IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

NOTE 2: MAXIMUM DIAMETER LEADS AT A GAUGING PLANE  $0.054'' + 0.001'' - 0.000''$  BELOW SEATING PLANE TO BE WITHIN  $0.007''$  OF THEIR TRUE LOCATION RELATIVE TO MAXIMUM WIDTH TAB AND TO THE MAXIMUM  $0.230''$  DIAMETER MEASURED WITH A SUITABLE GAUGE. WHEN GAUGE IS USED, MEASUREMENT WILL BE MADE AT SEATING PLANE.

NOTE 3: FOR VISUAL ORIENTATION ONLY.

NOTE 4: TAB LENGTH TO BE  $0.028''$  MINIMUM AND  $0.048''$  MAXIMUM, AND WILL BE DETERMINED BY SUBTRACTING DIAMETER "A" FROM DIMENSION "B".



# 2N709

## Transistor

### SILICON N-P-N EPITAXIAL-PLANAR TYPE

For Ultra-High-Speed Logic-Circuit Switching Applications  
in Commercial and Military Data-Processing Systems.  
The 2N2475 is a Direct Replacement for Type 2N709.

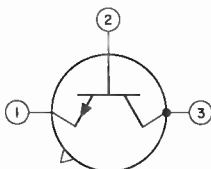
#### GENERAL DATA

##### Mechanical:

Dimensions . . . . . See *Outline TO-18* in General Section

Terminal Diagram: **BOTTOM VIEW**

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector,  
Case

#### SWITCHING SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values:*

COLLECTOR-TO-BASE VOLTAGE:

With emitter open . . . . .  $V_{CBO}$  15 max. volts

COLLECTOR-TO-EMITTER VOLTAGE:

With base open . . . . .  $V_{CEO}$  6 max. volts

EMITTER-TO-BASE VOLTAGE:

With collector open . . . . .  $V_{EBO}$  4 max. volts

COLLECTOR CURRENT . . . . .  $I_C$  Limited by power  
dissipation

TRANSISTOR DISSIPATION:<sup>a</sup> P

At case temperature<sup>b</sup> of  
100° C or below . . . . . 500 max. mw

At free-air temperature of  
25° C or below . . . . . 300 max. mw

TEMPERATURE RANGE:

Junction (Operating) . . . . .  $T_J$  -65 to +200 °C

Storage . . . . .  $T_{STG}$  -65 to +300 °C

LEAD TEMPERATURE:<sup>c</sup>

For 10 seconds maximum . . . . .  $T_L$  300 max. °C

#### ELECTRICAL CHARACTERISTICS

*Unless otherwise specified, free-air temperature = 25° C*

*Min. Typical Max.*

DC Collector Breakdown Voltage

for dc collector ma. = 0.01,

dc emitter current = 0 . . . BV<sub>CBO</sub> 15 30 - volts

<sup>a</sup> See accompanying *Rating Chart*.

<sup>b</sup> Measured at center of seating plane.

<sup>c</sup> Measured 1/16" ± 1/32" along lead, down from seating plane.



# 2N709

Min. Typical Max.

DC Emitter Breakdown Voltage for dc collector current = 0, dc emitter ma. = 0.01 . . . . .	$BV_{EBO}$	4	7	-	volts
DC Collector-to-Emitter Sustaining Voltage <sup>d</sup> for dc pulsed collector ma. = 10, dc base cur- rent = 0 . . . . .	$V_{CEO(sus)}$	6	10	-	volts
DC Base-to-Emitter Satu- ration Voltage for dc collector ma. = 3, dc base ma. = 0.15. . . . .	$V_{BE(sat)}$	0.7	0.77	0.85	volt
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = 3, dc base ma. = 0.15. . . . .	$V_{CE(sat)}$	-	0.26	0.3	volt
DC Collector-Cutoff Current for dc col- lector-to-base volts = 5, dc emitter current = 0, free-air tempera- ture = 25° C . . . . . 150° C . . . . .	$I_{CBO}$	-	0.002 0.9	0.05 5	$\mu a$ $\mu a$
Emitter-to-Base Capaci- tance for dc emitter-to- base volts = -0.5, dc collector current = 0, frequency (kc) = 140 (Approx.) . . . . .	$C_{ib}$	-	1.8	2	pf
Collector-to-Base Capaci- tance for dc collector- to-base volts = 5, dc emitter current = 0, frequency (kc) = 140 (Approx.) . . . . .	$C_{ob}$	-	2.1	3	pf
DC Forward-Current Transfer Ratio: With dc collector-to- emitter volts = 1, dc pulsed collector ma. = 30 . . . . . With dc collector-to- emitter volts = 0.5, dc pulsed collector ma. = 10 . . . . . With dc collector-to- emitter volts = 0.5, dc pulsed collector ma. = 10, free-air temperature = -55° C .	$h_{FE}$	15 20 10	43 53 29	- 120 -	





Small-Signal Short-Circuit  
Forward-Current Transfer  
Ratio for dc collector-  
to-emitter volts = 4,  
dc collector ma. = 5,  
signal frequency (Mc)  
= 100. . . . .

$h_{fe}$  6 8 -

Switching Time:

Storage time<sup>e</sup> for dc  
collector ma. = 5,  
turn-on dc base ma.  
= 5, turn-off dc base  
ma. = -5 . . . . .

$t_s$  - 4.1 6 nsec

Turn-On time<sup>f</sup> (Delay  
time + rise time) for  
dc collector ma. = 10,  
turn-on dc base ma.  
= 2, turn-off dc base  
ma. = -1 . . . . .

$t_{on}$  - 6.4 15 nsec

Turn-Off time<sup>f</sup> (Storage  
time + fall time) for  
dc collector ma. = 10,  
turn-on dc base ma.  
= 1, turn-off dc base  
ma. = -1 . . . . .

$t_{off}$  - 8.3 15 nsec

<sup>d</sup> The Collector-to-Emitter Sustaining Voltage [ $V_{CE0(sus)}$ ] with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{CEM} = 1$ : voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

<sup>e</sup> See accompanying *Storage-Time-Measurement Circuit*.

<sup>f</sup> See accompanying *Turn-On-Time and Turn-Off-Time Measurement Circuit*.

OPERATING CONSIDERATIONS,  
RATING CHART,  
STORAGE-TIME MEASUREMENT CIRCUIT,  
TURN-ON-TIME AND TURN-OFF-TIME MEASUREMENT CIRCUIT,  
and ASSOCIATED WAVE FORMS  
shown under type 2N2475 also apply to the 2N709





## Mesa Transistor

## GERMANIUM P-N-P DIFFUSED-BASE TYPE

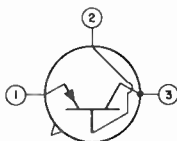
For Logic-Circuit Applications in Commercial  
and Military Data-Processing Equipment

## GENERAL DATA

## Mechanical:

Operating Position. . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.210"
Maximum Diameter. . . . .	0.230"
Dimensional Outline . . . . .	JEDEC No. TO-18
Case. . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length. . . . .	0.500"
Orientation and diameter. . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector,  
Case

## SWITCHING SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values:*

COLLECTOR-TO-BASE VOLTAGE . . . . .	-15 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE. . . . .	-15 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-2 max.	volts
COLLECTOR CURRENT . . . . .	-50 max.	ma
EMITTER CURRENT . . . . .	50 max.	ma

## TRANSISTOR DISSIPATION:

Operation in free air (See *Rating Chart*):

At ambient temperature of 25° C . . . . .	150 max.	mw
At ambient temperature of 55° C . . . . .	90 max.	mw
At ambient temperature of 71° C . . . . .	58 max.	mw

Operation with heat sink:

At case temperature of 25° C <sup>a</sup> . . . . .	300 max.	mw
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## AMBIENT TEMPERATURE RANGE:

Operating and storage . . . . .	-65 to +100	°C
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## LEAD TEMPERATURE:

For immersion in molten solder for 10 seconds maximum. . . . .	230 max.	°C
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<sup>a</sup> For case temperatures above 25° C, reduce the dissipation by 4 milli-watts/°C.



# 2N710

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base unless otherwise specified. Ambient temperature of 25° C.

Min. Typical Max.

DC Collector Breakdown Voltage for dc collector ma. = -0.1, emitter current = 0 . . .	$BV_{CBO}$	-15	-	-	volts
DC Emitter Breakdown Voltage for dc emitter ma. = -0.1, collector current = 0 . . .	$BV_{EBO}$	-2	-	-	volts
DC Collector-to-Emitter Breakdown Voltage for dc emitter volts = 0, dc collector ma. = -0.1 . . . . .	$BV_{CES}$	-15	-	-	volts
DC Base-to-Emitter Voltage for dc collector ma. = -10, dc base ma. = -0.4 . . . . .	$V_{BE}$	-0.34	-	-0.5	volt
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = -10, dc base ma. = -0.4 . . . . .	$V_{CE(sat)}$	-	-	-0.5	volt
DC Collector-Cutoff Current for dc collector volts = -5, emitter current = 0 . . . . .	$I_{CBO}$	-	-	-3	$\mu a$
Small-Signal Current Transfer Ratio for dc collector-to-emitter volts = -5, dc collector ma. = -10, frequency (Mc) = 100 . . . . .	$h_{fe}$	-	3	-	
DC Current Transfer Ratio for dc collector-to-emitter volts = -0.5, dc collector ma. = -10 . . . . .	$h_{FE}$	25	-	-	
Collector Transition Capacitance for dc collector volts = -10, emitter current = 0, frequency (Mc) = 1 . . . . .	$C_{TC}$	-	5	-	$\mu f$
Emitter Transition Capacitance for dc emitter volts = -2, collector current = 0, frequency (Mc) = 1 . . . . .	$C_{TE}$	-	3.5	-	$\mu f$



<p>"Turn-On" Time (Delay time + rise time) for dc collector-to-emitter supply volts = -3.5, "turn-on" base ma. = -1, collector resistor (ohms) = 300, dc "off" base-to-emitter volts = 0.5 . . . . .</p>	$t_d + t_r$	-	-	75 $\mu\text{sec}$
<p>Storage Time for dc collector-to-emitter supply volts = -3.5, "turn-on" base ma. = -1, "turn-off" base ma. = 0.25, collector resistor (ohms) = 300 . . . . .</p>	$t_s$	-	-	100 $\mu\text{sec}$
<p>Fall Time for dc collector-to-emitter supply volts = -3.5, "turn-on" base ma. = -1, "turn-off" base ma. = 0.25, collector resistor (ohms) = 300 . . . . .</p>	$t_f$	-	-	100 $\mu\text{sec}$

**PERFORMANCE TESTS,  
OPERATING CONSIDERATIONS,  
SWITCHING-TIME TEST CIRCUITS,  
and**

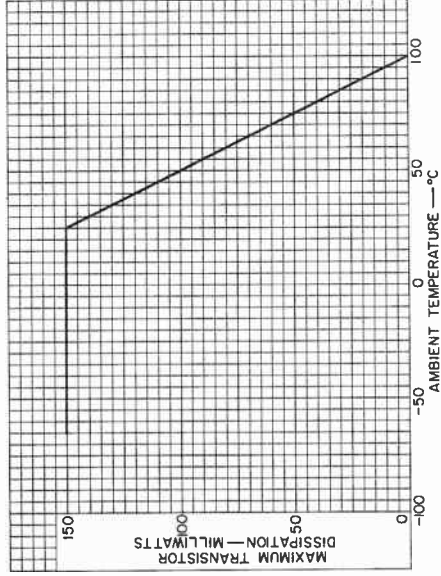
**DIMENSIONAL OUTLINE**

shown under Type 2N705 also apply to the 2N710



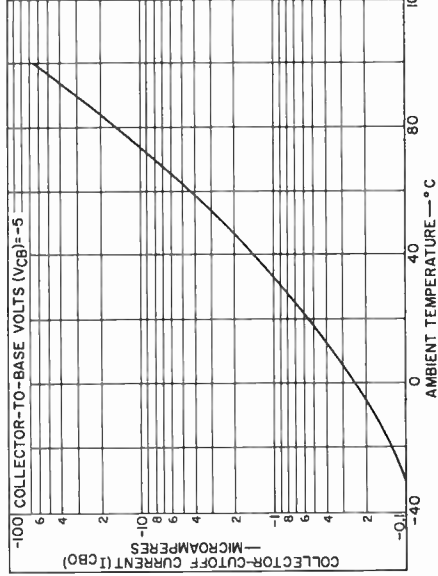
# 2N710

## RATING CHART



92CS-10968

## TYPICAL COLLECTOR-CUTOFF CURRENT CHARACTERISTIC

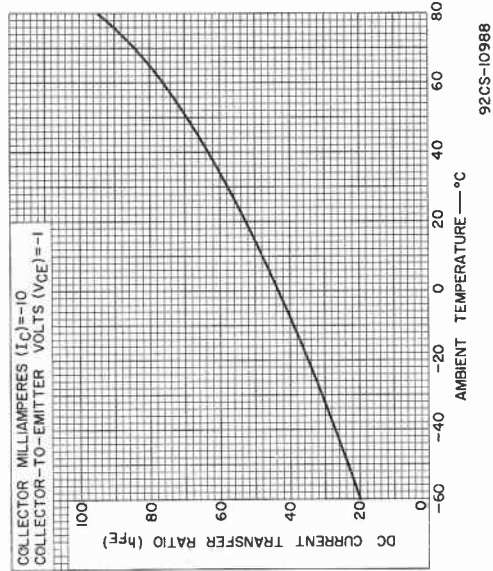
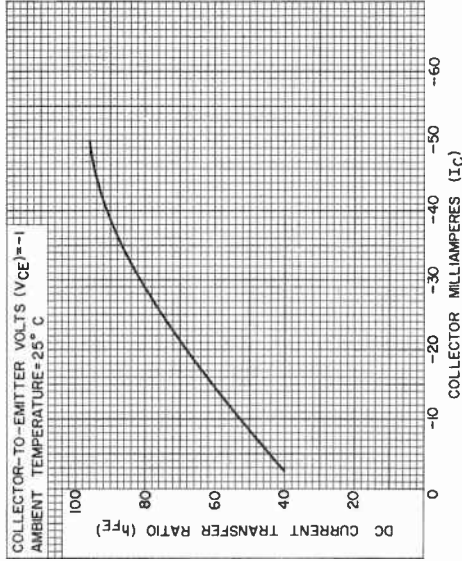


92CS-10976

**RCA**  
RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division  
Somerville, N. J.

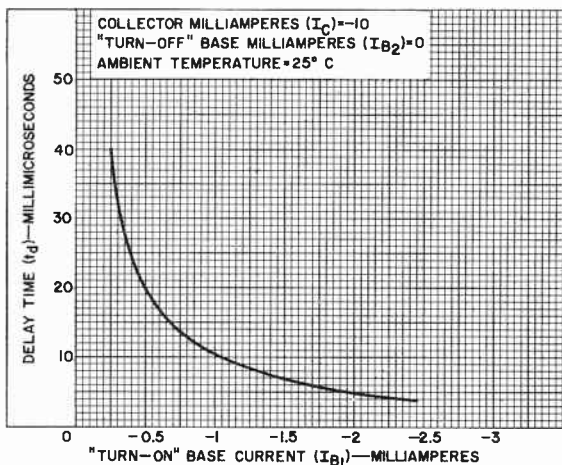


## TYPICAL DC-CURRENT-TRANSFER-RATIO CHARACTERISTICS

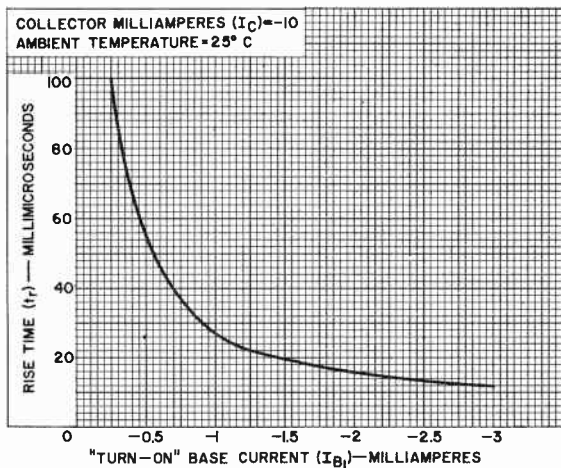


# 2N710

## TYPICAL CHARACTERISTICS



92CS-10984

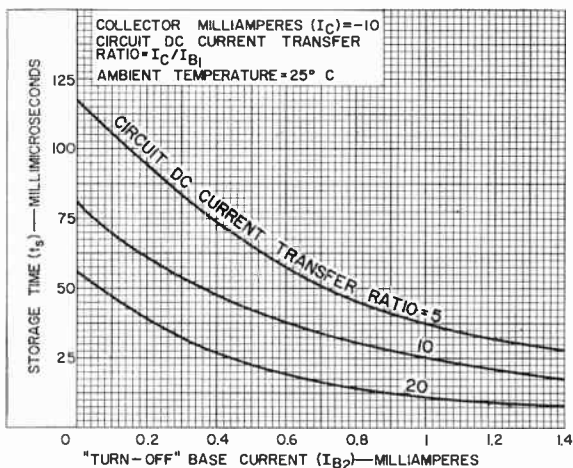


92CS-10985

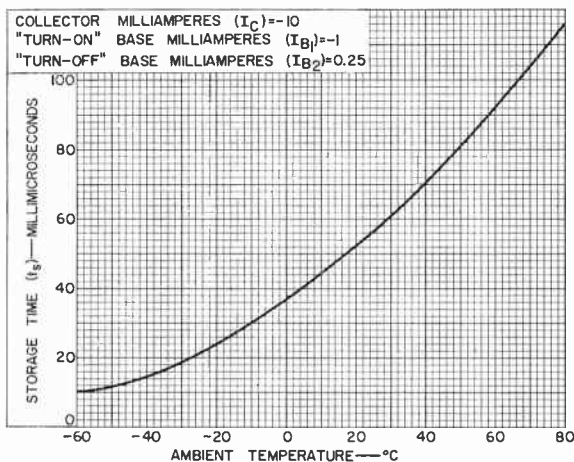




## TYPICAL STORAGE-TIME CHARACTERISTICS



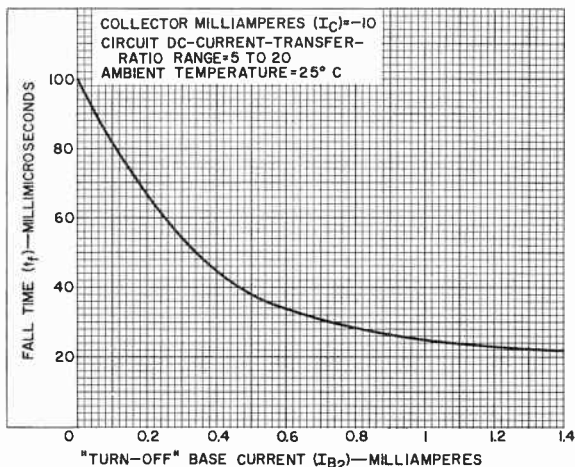
92CS-10975



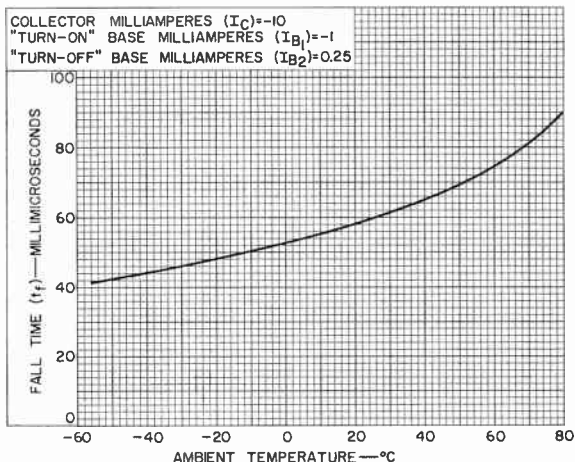
92CS-10973



## TYPICAL FALL-TIME CHARACTERISTICS



92CS-10989



92CS-10987

## Mesa Transistor

## GERMANIUM P-N-P DIFFUSED-BASE TYPE

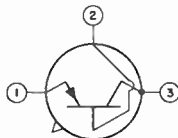
For Logic-Circuit Applications in Commercial  
and Military Data-Processing Equipment

## GENERAL DATA

## Mechanical:

Operating Position. . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.210"
Maximum Diameter. . . . .	0.230"
Dimensional Outline . . . . .	JEDEC No. TO-18
Case. . . . .	Metal
Seals. . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length. . . . .	0.500"
Orientation and diameter. . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector,  
Case

## SWITCHING SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values*:

COLLECTOR-TO-BASE VOLTAGE . . . . .	-12 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE. . . . .	-12 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-1 max.	volt
COLLECTOR CURRENT . . . . .	-100 max.	ma
EMITTER CURRENT . . . . .	100 max.	ma

## TRANSISTOR DISSIPATION:

Operation in free air (See *Rating Chart*):

At ambient temperature of 25° C . . . . .	150 max.	mw
At ambient temperature of 55° C . . . . .	90 max.	mw
At ambient temperature of 71° C . . . . .	58 max.	mw

Operation with heat sink:

At case temperature of 25° C <sup>a</sup> . . . . .	300 max.	mw
---	----------	----

## AMBIENT-TEMPERATURE RANGE:

Operating and storage . . . . .	-65 to +100	°C
---------------------------------	-------------	----

## LEAD TEMPERATURE:

For immersion in molten solder for 10 seconds maximum. . . . .	230 max.	°C
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<sup>a</sup> For case temperatures above 25° C, reduce the dissipation by 4 milli-watts/°C.



# 2N711

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base unless otherwise specified. Ambient temperature of 25° C.

Min. Typical Max.

DC Collector Breakdown Voltage for dc collector ma. = -0.1, emitter current = 0 . . . . .	$BV_{CBO}$	-12	-	-	volts
DC Emitter Breakdown Voltage for dc emitter ma. = -0.1, collector current = 0 . . . . .	$BV_{EBO}$	-1	-	-	volt
DC Collector-to-Emitter Breakdown Voltage for dc emitter volts = 0, dc collector ma. = -0.1 . . . . .	$BV_{CES}$	-12	-	-	volts
DC Base-to-Emitter Voltage for dc collector ma. = -10, dc base ma. = -0.4 . . . . .	$V_{BE}$	-0.34	-	-0.5	volt
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = -10, dc base ma. = -0.5 . . . . .	$V_{CE(sat)}$	-	-	-0.5	volt
DC Collector-Cutoff Current for dc collector volts = -5, emitter current = 0 . . . . .	$I_{CBO}$	-	-	-3	$\mu$ a
Small-Signal Current Transfer Ratio for dc collector-to-emitter volts = -5, dc collector ma. = -10, frequency (Mc) = 100 . . . . .	$h_{fe}$	-	2	-	
DC Current Transfer Ratio for dc collector-to-emitter volts = -0.5, dc collector ma. = -10 . . . . .	$h_{FE}$	20	-	-	
Collector Transition Capacitance for dc collector volts = -10, emitter current = 0, frequency (Mc) = 1 . . . . .	$C_{TC}$	-	5	-	$\mu$ f
Emitter Transition Capacitance for dc emitter volts = -2, collector current = 0, frequency (Mc) = 1 . . . . .	$C_{TE}$	-	4	-	$\mu$ f



"Turn-On" Time (Delay time + rise time) for dc collector-to-emitter supply volts = -3.5, "turn-on" base ma. = -1, collector resistor (ohms) = 300, dc "off" base-to-emitter volts = 0.5 . . . . .	$t_d + t_r$	-	-	100	$\mu\text{sec}$
Storage Time for dc collector-to-emitter supply volts = -3.5, "turn-on" base ma. = -1, "turn-off" base ma. = 0.25, collector resistor (ohms) = 300 . . . . .	$t_s$	-	-	200	$\mu\text{sec}$
Fall Time for dc collector-to-emitter supply volts = -3.5, "turn-on" base ma. = -1, "turn-off" base ma. = 0.25, collector resistor (ohms) = 300 . . . . .	$t_f$	-	-	150	$\mu\text{sec}$

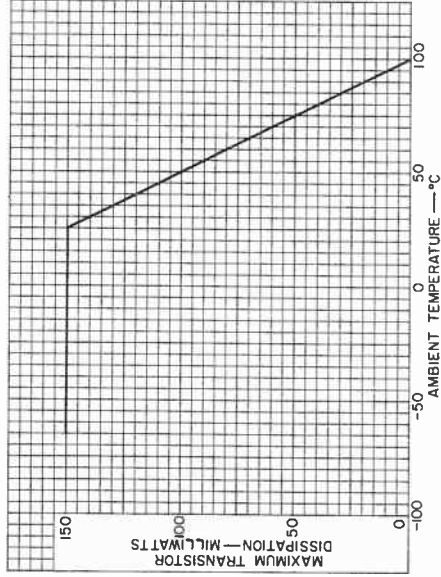
PERFORMANCE TESTS,  
OPERATING CONSIDERATIONS,  
SWITCHING-TIME TEST CIRCUITS,  
and  
DIMENSIONAL OUTLINE

shown under Type 2N705 also apply to the 2N711



# 2N711

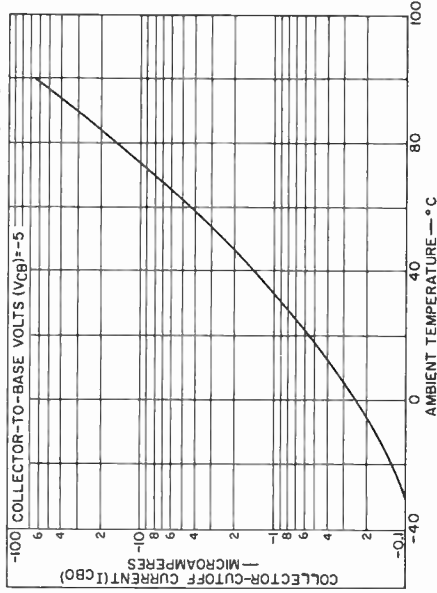
## RATING CHART



World Precision

92CS-10968

## TYPICAL COLLECTOR-CUTOFF-CURRENT CHARACTERISTIC



92CS-10976

RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division

Somerville, N. J.



## Mesa Transistor

### GERMANIUM P-N-P DIFFUSED-JUNCTION TYPE

For High-Speed Switching Service in Commercial and Military Data-Processing Systems

The 2N794 is the same as the 2N1300 except for the following items:

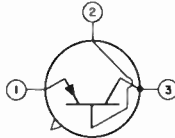
#### Mechanical:

Operating Position. . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.210"
Maximum Diameter. . . . .	0.230"
Dimensional Outline . . . . .	JFDEC No. TO-18
Case. . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length. . . . .	0.500"
Orientation and diameter. . . . .	See <i>Dimensional Outline</i>

Terminal Diagram:

BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



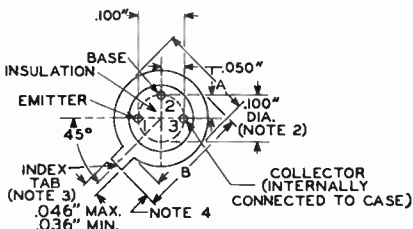
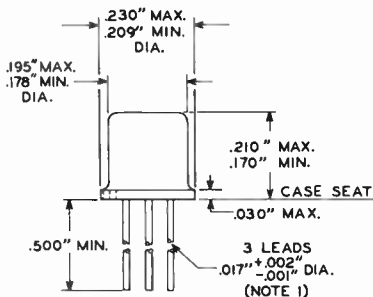
Lead 3 - Collector,  
Case

### OPERATING CONSIDERATIONS

It is to be noted that the case of this transistor operates at the collector voltage. Consideration, therefore, should be given to the possibility of shock hazard, if the case of this transistor is to operate at a voltage appreciably above or below ground potential. In such cases, suitable precautionary measures should be taken.



JEDEC No. T0-18



92CS-10605RI

NOTE 1: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE CASE SEAT. BETWEEN 0.25" TO THE END OF THE LEAD A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

NOTE 2: MAXIMUM DIAMETER LEADS AT A GAUGING PLANE 0.054"  $\pm$  0.001" - 0.000" BELOW CASE SEAT TO BE WITHIN 0.007" OF THEIR TRUE LOCATION RELATIVE TO MAXIMUM WIDTH TAB AND TO THE MAXIMUM 0.230" DIAMETER MEASURED WITH A SUITABLE GAUGE. WHEN GAUGE IS USED, MEASUREMENT WILL BE MADE AT CASE SEAT.

NOTE 3: FOR VISUAL ORIENTATION ONLY.

NOTE 4: TAB LENGTH TO BE 0.02B" MINIMUM AND 0.04B" MAXIMUM, AND WILL BE DETERMINED BY SUBTRACTING DIAMETER "A" FROM DIMENSION "B".



## Mesa Transistor

GERMANIUM P-N-P DIFFUSED-JUNCTION TYPE  
For High-Speed Switching Service in Commercial and Military Data-Processing Systems

The 2N795 is the same as the 2N1301 except for the following items:

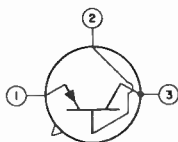
## Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.210"
Maximum Diameter . . . . .	0.230"
Dimensional Outline . . . . .	JEDEC No. TO-18
Case . . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	0.500"
Orientation and diameter . . . . .	See Dimensional Outline

Terminal Diagram: BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base



Lead 3 - Collector,  
Case

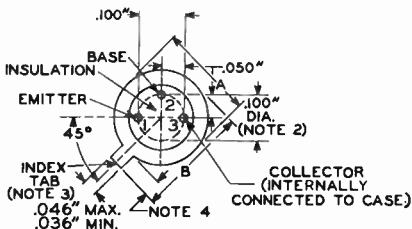
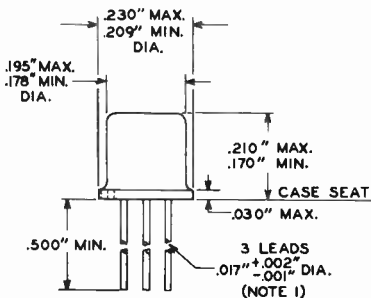
## OPERATING CONSIDERATIONS

It is to be noted that the case of this transistor operates at the collector voltage. Consideration, therefore, should be given to the possibility of shock hazard, if the case of this transistor is to operate at a voltage appreciably above or below ground potential. In such cases, suitable precautionary measures should be taken.



# 2N795

JEDEC No. T0-18



92CS-10605RI

**NOTE 1:** THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE CASE SEAT. BETWEEN 0.25" TO THE END OF THE LEAD A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

**NOTE 2:** MAXIMUM DIAMETER LEADS AT A GAUGING PLANE 0.054" + 0.001" - 0.000" BELOW CASE SEAT TO BE WITHIN 0.007" OF THEIR TRUE LOCATION RELATIVE TO MAXIMUM WIDTH TAB AND TO THE MAXIMUM 0.230" DIAMETER MEASURED WITH A SUITABLE GAUGE. WHEN GAUGE IS USED, MEASUREMENT WILL BE MADE AT CASE SEAT.

**NOTE 3:** FOR VISUAL ORIENTATION ONLY.

**NOTE 4:** TAB LENGTH TO BE 0.028" MINIMUM AND 0.048" MAXIMUM, AND WILL BE DETERMINED BY SUBTRACTING DIAMETER "A" FROM DIMENSION "B".

## Mesa Transistor

### GERMANIUM P-N-P DIFFUSED-JUNCTION TYPE

For High-Speed Switching Service in Commercial and Military Data-Processing Systems

The 2N796 is the same as the 2N1683 except for the following items:

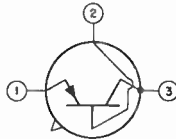
#### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.210"
Maximum Diameter . . . . .	0.230"
Dimensional Outline . . . . .	JEDEC No. TO-18
Case . . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	0.500"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>

Terminal Diagram:                      BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base



Lead 3 - Collector,  
Case

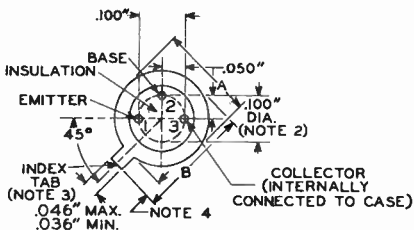
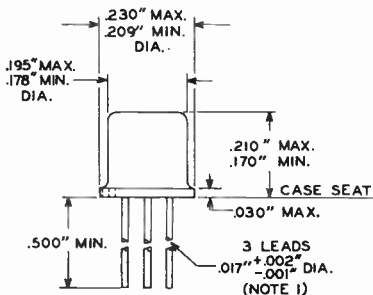
### OPERATING CONSIDERATIONS

It is to be noted that the case of this transistor operates at the collector voltage. Consideration, therefore, should be given to the possibility of shock hazard, if the case of this transistor is to operate at a voltage appreciably above or below ground potential. In such cases, suitable precautionary measures should be taken.



# 2N796

JEDEC No. T0-18



92CS-10605R1

NOTE 1: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN  $D.05''$  AND  $D.25''$  FROM THE CASE SEAT. BETWEEN  $D.25''$  TO THE END OF THE LEAD A MAXIMUM DIAMETER OF  $D.021''$  IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

NOTE 2: MAXIMUM DIAMETER LEADS AT A GAUGING PLANE  $D.054'' + D.001'' - D.003''$  BELOW CASE SEAT TO BE WITHIN  $D.007''$  OF THEIR TRUE LOCATION RELATIVE TO MAXIMUM WIDTH TAB AND TO THE MAXIMUM  $D.230''$  DIAMETER MEASURED WITH A SUITABLE GAUGE. WHEN GAUGE IS USED, MEASUREMENT WILL BE MADE AT CASE SEAT.

NOTE 3: FOR VISUAL ORIENTATION ONLY.

NOTE 4: TAB LENGTH TO BE  $0.028''$  MINIMUM AND  $0.048''$  MAXIMUM, AND WILL BE DETERMINED BY SUBTRACTING DIAMETER "A" FROM DIMENSION "B".

## Transistor

### GERMANIUM P-N-P DIFFUSED-JUNCTION EPITAXIAL-MESA TYPE

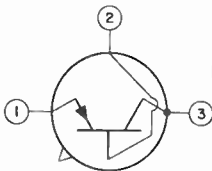
For Switching Applications in Industrial and Military Equipment

#### GENERAL DATA

##### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.210"
Maximum Diameter . . . . .	0.230"
Dimensional Outline . . . . .	JFEDC No. TO-18
Case . . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	0.500"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector,  
Case

#### SWITCHING SERVICE

##### Maximum and Minimum Ratings, *Absolute-Maximum Values:*

COLLECTOR-TO-BASE VOLTAGE:		
With emitter open . . . . .	-15 max.	volts
COLLECTOR-TO-EMITTER:		
With external resistor (ohms) $\leq 10$ between base and emitter . . . . .	-15 max.	volts
EMITTER-TO-BASE:		
With collector open . . . . .	-2.5 max.	volts
COLLECTOR CURRENT . . . . .	-200 max.	ma
TRANSISTOR DISSIPATION: <sup>a</sup>		
At case temperature <sup>b</sup> of 25°C or below . . . . .	300 max.	mw
At free-air temperature of 25°C or below . . . . .	150 max.	mw
TEMPERATURE RANGE:		
Storage . . . . .	-65 to +100	°C
Operating (Junction) . . . . .	100 max.	°C
LEAD TEMPERATURE:		
For 10 seconds maximum <sup>c</sup> . . . . .	240 max.	°C

<sup>a</sup> See accompanying *Rating Chart*.

<sup>b</sup> Measured at center of seating plane.

<sup>c</sup> Measured 1/16"  $\pm$  1/32" down from seating plane.



# 2N828

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base unless otherwise specified. Free-air temperature of 25° C.

		Min.	Max.	
DC Collector Breakdown Voltage for dc collector ma. = -0.1, emitter ma. = 0 . . . . .	$V_{CB0}$	-15	-	volts
DC Collector-to-Emitter Breakdown Voltage for dc base-to-emitter volts = 0, dc collector ma. = -0.1, external base-to-emitter resistance (ohms) = 0 . . . . .	$V_{CES}$	-15	-	volts
DC Emitter Breakdown Voltage for dc collector ma. = 0, dc emitter ma. = -0.1 . . . . .	$V_{EBO}$	-2.5	-	volts
DC Base-to-Emitter Saturation Voltage for dc collector ma. = -10, dc base ma. = -1 . . . . .	$V_{BE(sat)}$	0.34	0.44	volt
DC Collector-to-Emitter Saturation Voltage:	$V_{CE(sat)}$			
With dc collector ma. = -10, dc base ma. = -1 . . . . .		-	-0.2	volt
With dc collector ma. = -50, dc base ma. = -5 . . . . .		-	-0.25	volt
DC Collector-Cutoff Current for dc collector volts = -6, dc emitter ma. = 0 . . . . .	$I_{CBO}$	-	-3	$\mu a$
Collector-to-Base Capacitance for dc collector volts = -6, dc emitter ma. = 0, frequency (kc) = 100 . . . . .	$C_{ob}$	-	6	$\mu\mu f$
DC Current Transfer Ratio for dc collector-to-emitter volts = -0.3, dc collector ma. = -10 . . . . .	$h_{FE}$	25	-	
Small-Signal Current Transfer Ratio for dc collector-to-emitter volts = -1, dc collector ma. = -10, frequency (Mc) = 100 . . . . .	$h_{fe}$	3	-	
Gain-Bandwidth Product for dc collector-to-emitter volts = -1, dc collector ma. = -10 . . . . .	$f_T$	300	-	Mc
Switching Time <sup>d</sup> for the following conditions unless otherwise specified, with dc collector-to-emitter supply volts = -3, dc collector ma. = -10, "turn-on" base ma. = -1, "turn-off" base ma. = 0.25, external collector resistance (including "sampling" resistor of 20 ohms) of 300 ohms:				



"Turn-On" Time (Delay time  
+ rise time) for dc col-  
lector-to-emitter supply  
volts = -3.5, dc base-  
to-emitter (off) volts

= 1.25 . . . . .	$t_d + t_r$	-	70	$\mu\text{sec}$
Storage Time . . . . .	$t_s$	-	50	$\mu\text{sec}$
Fall Time . . . . .	$t_f$	-	50	$\mu\text{sec}$

#### Saturation Stored-Charge Time

Constant  $f$  for dc collector-to-  
emitter supply volts = -10, dc  
collector ma.<sup>e</sup> = -10, "turn-on"  
base ma. = -10, "turn-off" base  
ma. = 10, external collector  
resistance (including "sampling"  
resistor of 20 ohms) of  
1000 ohms . . . . .

$T_s$	-	25	$\mu\text{sec}$
-------	---	----	-----------------

<sup>d</sup> See accompanying *Switching-Time Measurement Circuit*.

<sup>e</sup> The dc collector-to-emitter supply volts adjusted to give dc collector milliamperes of -10.

<sup>f</sup> See accompanying *Saturation Stored-Charge Time Constant Measurement Circuit*.

## PERFORMANCE TESTS

This transistor type meets mechanical and environmental requirements of Military Specification MIL-S-19500B.

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the seating plane provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the seals of the leads and damage the transistor.

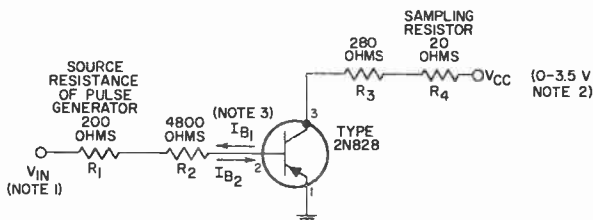
This transistor is intended for use in single-side printed-circuit boards and in conventional wire-in-type circuits. If this transistor is used in double-side printed-circuit boards or in printed-circuit boards utilizing eyelets, it may be necessary to use an insulating washer or similar standoff device made of good dielectric material to prevent the solder from shorting the leads to each other or to the board, and to prevent the collector from shorting to ground.

It is to be noted that the case of this transistor operates at the collector voltage. Consideration, therefore, should be given to the possibility of shock hazard, if the case of this transistor is to operate at a voltage appreciably above or below ground potential. In such cases, suitable precautionary measures should be taken.



# 2N828

## SWITCHING-TIME MEASUREMENT CIRCUIT



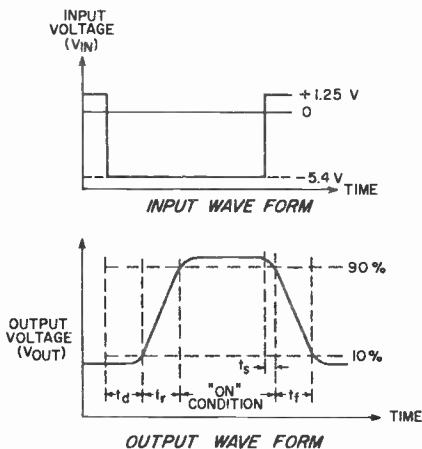
92CS-11308

**NOTE 1:** TEST CIRCUIT PROVIDED BY THE TEKTRONIX TYPE R PLUG-IN UNIT (FOR TEKTRONIX MODEL 541 OSCILLOSCOPE) FOR THE MEASUREMENT OF SWITCHING TIME. THE TYPE R UNIT PROVIDES THE INPUT VOLTAGE ( $V_{IN}$ ) AND THE COLLECTOR-SUPPLY VOLTAGE ( $V_{CC}$ ). RESISTORS  $R_1$  AND  $R_4$  ARE INCLUDED IN THE TYPE R UNIT; RESISTORS  $R_2$  AND  $R_3$  ARE WIRED TO THE ASSOCIATED WIRING BOARD.

**NOTE 2:**  $V_{CC}$  IS ADJUSTED FOR  $I_C = -10$  MA.

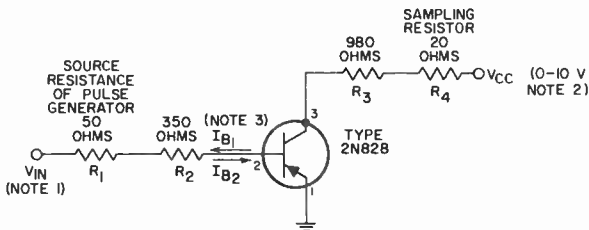
**NOTE 3:**  $I_{B1}$  = "TURN-ON" BASE CURRENT = -1 MA.  
 $I_{B2}$  = "TURN-OFF" BASE CURRENT = 0.25 MA.

## ASSOCIATED WAVE FORMS



92CS-11312



SATURATION STORED-CHARGE TIME CONSTANT  
MEASUREMENT CIRCUIT

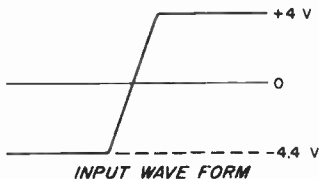
92CS-11309

NOTE 1: TEST CIRCUIT PROVIDED BY THE TEKTRONIX TYPE R PLUG-IN UNIT (FOR TEKTRONIX MODEL 541 OSCILLOSCOPE) FOR THE MEASUREMENT OF  $\tau_S$ . THE TYPE R UNIT PROVIDES THE INPUT VOLTAGE ( $V_{IN}$ ) AND THE COLLECTOR-SUPPLY VOLTAGE ( $V_{CC}$ ). RESISTORS  $R_1$  AND  $R_4$  ARE INCLUDED IN THE TYPE R UNIT; RESISTORS  $R_2$  AND  $R_3$  ARE WIRED TO THE ASSOCIATED WIRING BOARD.

NOTE 2:  $V_{CC}$  IS ADJUSTED FOR  $I_C = -10$  MA.

NOTE 3:  $I_{B1}$  = "TURN-ON" BASE CURRENT = -10 MA.  
 $I_{B2}$  = "TURN-OFF" BASE CURRENT = 10 MA.

## ASSOCIATED WAVE FORM

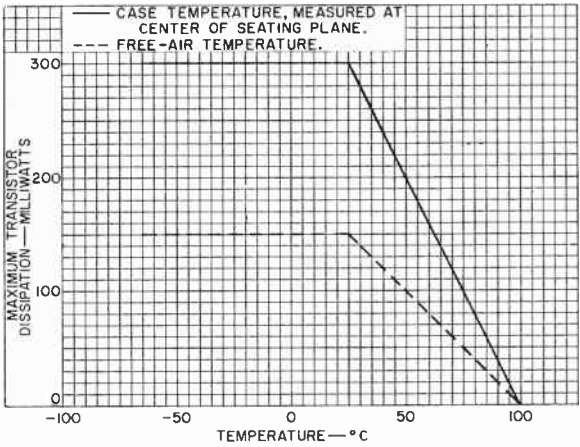


92CS-11311





## RATING CHART



92CS-11307R1





# 2N955

## Transistor

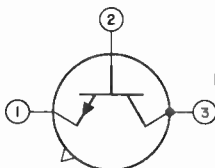
### GERMANIUM P-N-P DOUBLE-DIFFUSED-JUNCTION TYPE

For High-Speed Logic-Circuit Switching Applications  
in Commercial and Military Data-Processing Systems.  
The 2N955A is a Direct Replacement for Type 2N955.

#### GENERAL DATA

##### Mechanical:

Dimensions . . . . . See Outline T0-18 in General Section  
Terminal Diagram: BOTTOM VIEW



Lead 1 - Emitter  
Lead 2 - Base

Lead 3 - Collector,  
Case

#### SWITCHING SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values*:

##### COLLECTOR-TO-BASE VOLTAGE:

With emitter open. . . . .  $V_{CBO}$  12 max. volts

##### COLLECTOR-TO-EMITTER VOLTAGE:

With base open . . . . .  $V_{CEO}$  8 max. volts ←

##### EMITTER-TO-BASE VOLTAGE:

With collector open. . . . .  $V_{EBO}$  2 max. volts

##### COLLECTOR CURRENT. . . . . $I_C$

100 max. ma

##### TRANSISTOR DISSIPATION:<sup>a</sup>

At free-air temperature of  
25° C or below . . . . . 150 max. mw

##### TEMPERATURE RANGE:

Junction (Operating) . . . . .  $T_J$  -65 to +100 °C

Storage. . . . .  $T_{STG}$  -65 to +100 °C

##### LEAD TEMPERATURE:<sup>b</sup>

For 10 seconds maximum . . . . .  $T_L$  230 max. °C

#### ELECTRICAL CHARACTERISTICS

*Free-air temperature = 25° C*

*Min. Typical Max.*

##### DC Collector-to-Base

Breakdown Voltage for dc

collector ma. = 0.1, dc

emitter current = 0. . . . .  $BV_{CBO}$

12 25 - volts

<sup>a</sup> See accompanying Rating Chart.

<sup>b</sup> Measured 1/16" ± 1/32" along lead, down from seating plane.

← Indicates a change.



# 2N955

Min. Typical Max.

DC Collector-to-Emitter Breakdown Voltage for dc collector ma. = 5, dc emitter current = 0.	$V_{CE0}$	8	15	-	volts
DC Emitter-to-Base Breakdown Voltage for dc collector current = 0, dc emitter ma. = 0.1 . . . . .	$V_{EBO}$	2	6	-	volts
DC Collector-to-Emitter Reach-Through Voltage for dc collector-to-base volts = 12, dc emitter-to-base floating potential (volts) = 1 . . . . .	$V_{RT}$	11	-	-	volts
DC Collector-to-Emitter Latching Voltage for dc collector ma. = 100, external base-to-emitter resistance (ohms) = 1000 . . . . .	$V_{CERL}^c$	9	-	-	volts
DC Base-to-Emitter Saturation Voltage for dc collector ma. = 30, dc base ma. = 1 . . . . .	$V_{BE}(sat)$	0.3	0.45	0.6	volt
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = 30, dc base ma. = 1 . . . . .	$V_{CE}(sat)$	-	0.35	0.5	volt
DC Collector-Cutoff Current for dc collector volts = 5, dc emitter current = 0 . . . . .	$I_{CBO}$	-	0.6	5	$\mu a$
Input Capacitance for dc emitter-to-base volts = -0.5, dc collector current = 0, signal frequency (kc) = 100 . . . . .	$C_{ib}$	-	6	10	pf
Output Capacitance for dc collector-to-base volts = 5, dc emitter current = 0, frequency (kc) = 100 . . . . .	$C_{ob}$	-	4	6	pf
DC Forward-Current Transfer Ratio for dc collector-to-base volts = 0.5, dc collector ma. = 30 . . . . .	$h_{FE}$	30	50	-	



## Small-Signal Short-Circuit

Forward Current Transfer  
Ratio for dc collector-  
to-emitter volts = 5, dc  
collector ma. = 20,  
signal frequency (Mc)  
= 100. . . . .

$h_{fe}$  - 10 -

Total Stored Charge for  
dc collector ma. = 30,  
dc base ma. = 1.5. . . .

$Q_s^d$  - 90 - pc

Switching Time for dc  
collector supply volts  
= 5, dc collector ma.  
= 30:

Delay time for dc base  
supply volts = -0.5,  
dc base-to-emitter  
volts = -0.5, turn-on  
dc base ma. = 4. . . .

$t_d^e$  - 4.5 - nsec

Rise time for dc base  
supply volts = -0.5,  
dc base-to-emitter  
volts = -0.5, turn-on  
dc base ma. = 4. . . .

$t_r^e$  - 6.5 10 nsec

Storage time for dc base  
supply volts = 5,  
turn-on dc base ma. =  
1.5, turn-off dc base  
ma. = -3. . . . .

$t_s^f$  - 18 - nsec

Fall time for dc base  
supply volts = 5,  
turn-on dc base ma. =  
1.5, turn-off dc base  
ma. = -3. . . . .

$t_f^f$  - 8 - nsec

Total turn-off time for  
dc base supply volts  
= 5, turn-on dc base  
ma. = 1.5, total  
stored charge (pf)  
= 125. . . . .

$t_{Q_s}^d$  - 9 15 nsec

<sup>c</sup> See accompanying DC Collector-to-Emitter Latching-Voltage ( $V_{CERL}$ ) Measurement Circuit.

<sup>d</sup> See accompanying Total-Stored-Charge ( $Q_s$ ) and Total Turn-Off Time ( $t_{Q_s}$ ) Measurement Circuit.

<sup>e</sup> See accompanying Delay-Time ( $t_d$ ) and Rise-Time ( $t_r$ ) Measurement Circuit.

<sup>f</sup> See accompanying Storage-Time ( $t_s$ ) and Fall-Time ( $t_f$ ) Measurement Circuit.



# 2N955

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OPERATING CONSIDERATIONS,  
DC COLLECTOR-TO-EMITTER LATCHING VOLTAGE ( $V_{CERL}$ )  
MEASUREMENT CIRCUIT,  
TOTAL-STORED-CHARGE ( $Q_s$ ) and TOTAL TURN-OFF TIME ( $t_{Qs}$ )  
MEASUREMENT CIRCUIT,  
DELAY-TIME ( $t_d$ ) and RISE-TIME ( $t_r$ ) MEASUREMENT CIRCUIT,  
STORAGE-TIME ( $t_s$ ) and FALL-TIME ( $t_f$ ) MEASUREMENT CIRCUIT,  
and  
RATING CHART  
shown under type 2N955A also apply to the 2N955





## Transistor

### GERMANIUM N-P-N DOUBLE-DIFFUSED-JUNCTION MESA TYPE

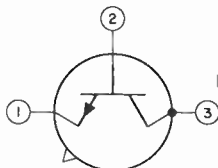
For Logic-Circuit Applications in Commercial  
and Military Data-Processing Equipment

#### GENERAL DATA

##### Mechanical:

Operating Position. . . . .	Any
Maximum Length (Excluding flexible leads). . . . .	0.210"
Maximum Diameter. . . . .	0.230"
Dimensional Outline . . . . .	JEDFC No. TO-18
Case. . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length. . . . .	0.500"
Orientation and diameter. . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector,  
Case

#### SWITCHING SERVICE

##### Maximum and Minimum Ratings, *Absolute-Maximum Values:*

COLLECTOR-TO-BASE VOLTAGE:		
With emitter open . . . . .	12 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With base open. . . . .	11 max.	volts
EMITTER-TO-BASE VOLTAGE:		
With collector open . . . . .	2 max.	volts
COLLECTOR CURRENT . . . . .	100 max.	ma
TRANSISTOR DISSIPATION: <sup>a</sup>		
At free-air temperature of 25°C or below. . . . .	150 max.	mw
FREE-AIR TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +100	°C
LEAD TEMPERATURE:		
For 10 seconds maximum <sup>b</sup> . . . . .	230 max.	°C

<sup>a</sup> See accompanying *Rating Chart*.

<sup>b</sup> Measured 1/16" ± 1/32" down from seating plane.



# 2N955

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base unless otherwise specified. Free-air temperature of 25° C.

Min. Typical Max.

DC Collector Breakdown					
Voltage for dc collector ma. = 0.1, dc emitter ma. = 0 . . . . .	$BV_{CBO}$	12	25	-	volts
DC Emitter Breakdown					
Voltage for dc collector ma. = 0, dc emitter ma. = 0.1 . . . . .	$BV_{EBO}$	2	5	-	volts
DC Collector-to-Emitter Reach-Through Voltage .	$V_{RT}$	11	-	-	volts
DC Collector-to-Emitter Latching Voltage for dc collector ma. = 100, external base-to- emitter resistance (ohms) = 1000 . . . . .	$V_{CERL}^c$	9	-	-	volts
DC Base-to-Emitter Saturation Voltage for dc collector ma. = 30, dc base ma. = 1 . . . . .	$V_{BE}(sat)$	0.3	0.45	0.6	volt
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = 30, dc base ma. = 1 . . . . .	$V_{CE}(sat)$	-	0.35	0.5	volt
DC Collector-Cutoff Current for dc collec- tor volts = 5, dc emitter ma. = 0 . . . . .	$I_{CBO}$	-	2	5	$\mu a$
Input Capacitance for dc emitter volts = 0.5, dc collector ma. = 0 . . . . .	$C_{ib}$	-	7	10	pf
Output Capacitance for dc collector volts = 5, dc emitter ma. = 0 . . . . .	$C_{ob}$	-	4	6	pf
Small-Signal Current Transfer Ratio for dc collector-to-emitter volts = 5, dc collector ma. = 20, frequency (Mc) = 100 . . . . .	$h_{fe}$	-	10	-	
DC Current Transfer Ratio for dc collector-to- emitter volts = 0.5, dc collector ma. = 30 . . . . .	$h_{FE}$	30	60	-	
Total Stored Charge for dc collector ma. = 30, dc base ma. = 1.5 . . . . .	$Q_s^d$	-	90	125	pc



## Delay Time:

 $t_d$ 

<sup>e</sup>With dc collector supply volts = 5, dc base supply volts = -0.5, "off" dc base-to-emitter volts = -0.5, dc collector ma. = 30, "on" dc base ma. = 4. . . . .

- 4.5 - nsec

<sup>f</sup>With dc collector supply volts = 3.5, dc base supply volts = -6, "off" dc base-to-emitter volts = -0.5, dc collector ma. = 10, "on" dc base ma. = 1. . . . .

- 11 - nsec

## Rise Time:

 $t_r$ 

<sup>e</sup>With dc collector supply volts = 5, dc base supply volts = -0.5, "off" dc base-to-emitter volts = -0.5, dc collector ma. = 30, "on" dc base ma. = 4. . . . .

- 6.5 10 nsec

<sup>f</sup>With dc collector supply volts = 3.5, dc base supply volts = -6, "off" dc base-to-emitter volts = -0.5, dc collector ma. = 10, "on" dc base ma. = 1. . . . .

- 20 - nsec

## Storage Time:

 $t_s$ 

<sup>g</sup>With dc collector supply volts = 5, dc base supply volts = 5, dc collector ma. = 30, "on" dc base ma. = 1.5, "off" dc base ma. = -3. . . . .

- 18 - nsec

<sup>h</sup>With dc collector supply volts = 3.5, dc base supply volts = 10, dc collector ma. = 10, "on" dc base ma. = 1, "off" dc base ma. = -0.25. . . . .

- 45 - nsec



# 2N955

Min. Typical Max.

	$t_f$			
Fall Time:				
<sup>g</sup> With dc collector supply volts = 5, dc base supply volts = 5, dc collector ma. = 30, "on" dc base ma. = 1.5, "off" dc base ma. = -3 . . . .	-	8	-	nsec
<sup>h</sup> With dc collector supply volts = 3.5, dc base supply volts = 10, dc collector ma. = 10, "on" dc base ma. = 1, "off" dc base ma. = -0.25 . . . .	-	50	-	nsec
Total Turn-Off Time for total stored charge (pc) = 125, dc collector supply volts = 5, dc base supply volts = 5, dc collector ma. = 30, "on" dc base ma. = 1.5 . . . . .	$t_{Q_S}^d$	-	9	15 nsec

<sup>c</sup> See accompanying DC Collector-to-Emitter Latching-Voltage ( $V_{CERL}$ ) Measurement Circuit.

<sup>d</sup> See accompanying Total-Stored-Charge ( $Q_S$ ) and Total Turn-Off Time ( $t_{Q_S}$ ) Measurement Circuit.

<sup>e</sup> See accompanying Delay-Time ( $t_d$ ) and Rise-Time ( $t_r$ ) Measurement Circuit.

<sup>f</sup> See accompanying Alternate-Delay-Time and Rise-Time Measurement Circuit.

<sup>g</sup> See accompanying Storage-Time ( $t_s$ ) and Fall-Time ( $t_f$ ) Measurement Circuit.

<sup>h</sup> See accompanying Alternate-Storage-Time and Fall-Time Measurement Circuit.

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The flexible leads of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the seating plane provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the seals of the leads and damage the transistor.

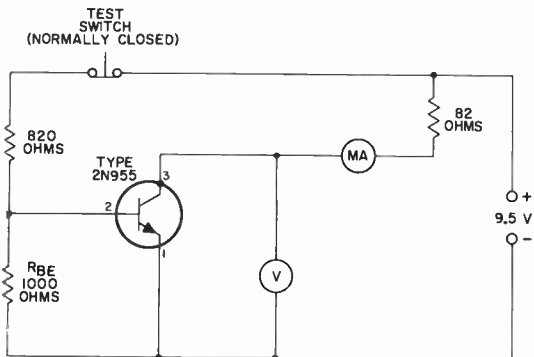
This transistor is intended for use in single-side printed-circuit boards and in conventional wire-in-type circuits. If this transistor is used in double-side printed-circuit boards or in printed-circuit boards utilizing eyelets, it may be necessary to use an insulating washer or similar standoff device made of good dielectric material to prevent the solder



from shorting the leads to each other or to the board, and to prevent the collector from shorting to ground.

It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.

### DC COLLECTOR-TO-EMITTER LATCHING-VOLTAGE ( $V_{CERL}$ ) MEASUREMENT CIRCUIT

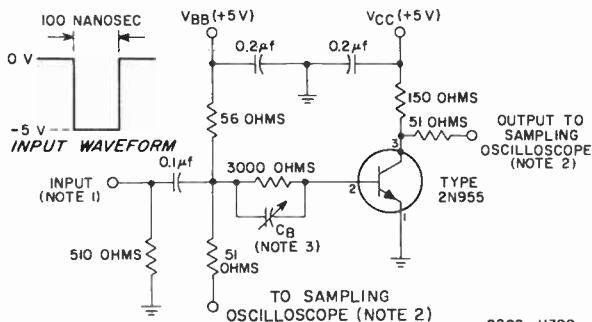


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# 2N955

## TOTAL-STORED-CHARGE ( $Q_s$ ) AND TOTAL TURN-OFF TIME ( $t_{Qs}$ ) MEASUREMENT CIRCUIT

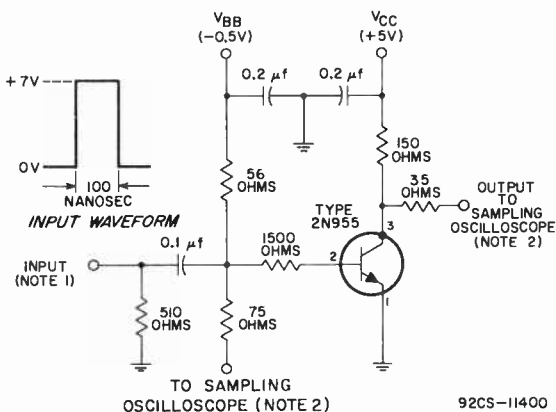


**NOTE 1:** FROM TEKTRONIX TYPE 110 MERCURY PULSER, OR EQUIVALENT.

**NOTE 2:** HEWLETT-PACKARD TYPE 185A, OR EQUIVALENT.

**NOTE 3:** FOR MEASUREMENT OF  $Q_s$ ,  $C_B$  IS A CALIBRATED VARIABLE CAPACITOR HAVING A RANGE OF APPROXIMATELY 3.5 TO 35 MICROMICROFARADS. FOR MEASUREMENT OF  $t_{Qs}$ ,  $C_B$  IS A FIXED CAPACITOR HAVING A VALUE OF 27 MICROMICROFARADS  $\pm$  2 PERCENT.

## DELAY-TIME ( $t_d$ ) AND RISE-TIME ( $t_r$ ) MEASUREMENT CIRCUIT

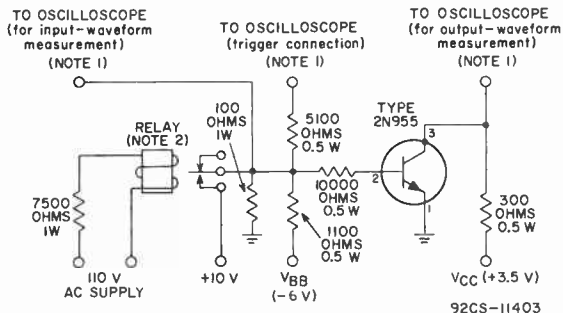


NOTE 1: FROM TEKTRONIX TYPE 110 MERCURY PULSER, OR EQUIVALENT.

NOTE 2: HEWLETT-PACKARD TYPE 185A, OR EQUIVALENT.

## ALTERNATE-DELAY-TIME AND RISE-TIME MEASUREMENT CIRCUIT

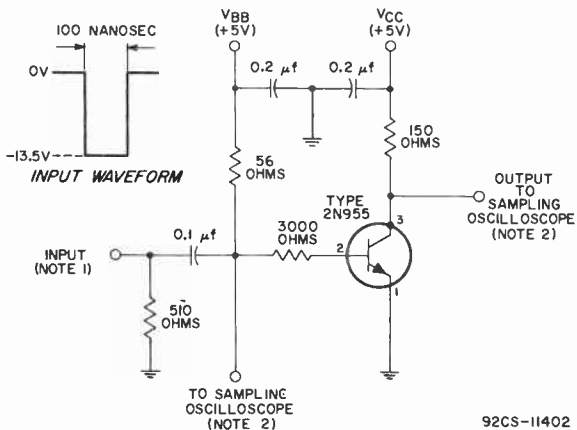
NOTE: Except for supply-voltage polarities, this circuit is identical with that used to measure "Turn-On" Time (Delay time + rise time) for Type 2N705.



NOTE 1: TEKTRONIX TYPE 545, OR EQUIVALENT.

NOTE 2: C.P. CLARE MERCURY RELAY TYPE HG-2A-1004, OR EQUIVALENT.

## STORAGE-TIME ( $t_s$ ) AND FALL-TIME ( $t_f$ ) MEASUREMENT CIRCUIT



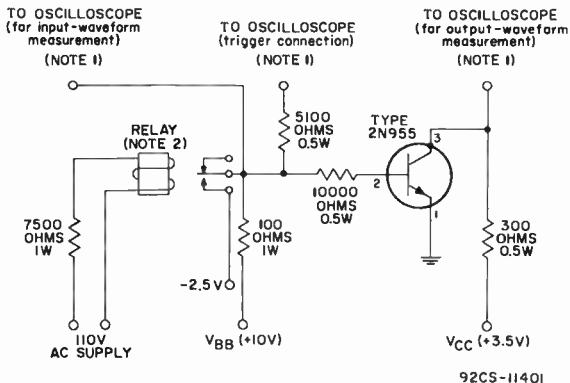
# 2N955

NOTE 1: FROM TEKTRONIX TYPE 110 MERCURY PULSER, OR EQUIVALENT.

NOTE 2: HEWLETT-PACKARD TYPE 185A, OR EQUIVALENT.

## ALTERNATE-STORAGE-TIME AND FALL-TIME MEASUREMENT CIRCUIT

NOTE: Except for supply-voltage polarities, this circuit is identical with that used to measure "Turn-Off" Storage Time and "Turn-Off" Fall Time for Type 2N705.

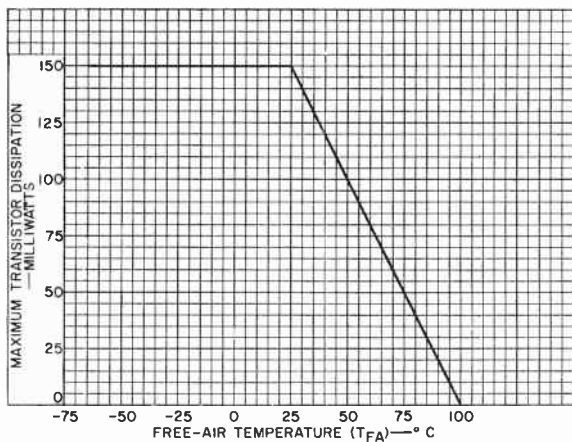


NOTE 1: TEKTRONIX TYPE 545, OR EQUIVALENT.

NOTE 2: C.P. CLARE MERCURY RELAY TYPE HG-2A-1004, OR EQUIVALENT.



## RATING CHART

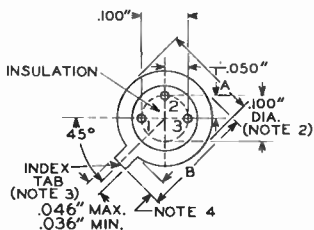
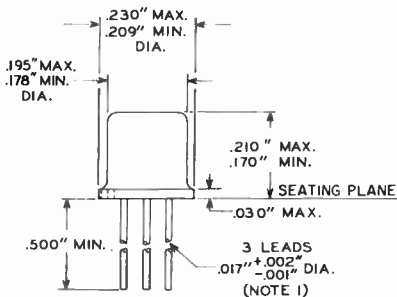


92CS-11404



# 2N955

JEDEC No. T0-18



92CS-10605R2

**NOTE 1:** THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN  $0.05''$  AND  $0.25''$  FROM THE SEATING PLANE. BETWEEN  $0.25''$  TO THE END OF THE LEAD, A MAXIMUM DIAMETER OF  $0.021''$  IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

**NOTE 2:** MAXIMUM DIAMETER LEADS AT A GAUGING PLANE  $0.054'' + 0.001'' - 0.000''$  BELOW SEATING PLANE TO BE WITHIN  $0.007''$  OF THEIR TRUE LOCATION RELATIVE TO MAXIMUM WIDTH TAB AND TO THE MAXIMUM  $0.230''$  DIAMETER MEASURED WITH A SUITABLE GAUGE. WHEN GAUGE IS USED, MEASUREMENT WILL BE MADE AT SEATING PLANE.

**NOTE 3:** FOR VISUAL ORIENTATION ONLY.

**NOTE 4:** TAB LENGTH TO BE  $0.028''$  MINIMUM AND  $0.048''$  MAXIMUM, AND WILL BE DETERMINED BY SUBTRACTING DIAMETER "A" FROM DIMENSION "B".

# 2N955A

## Transistor

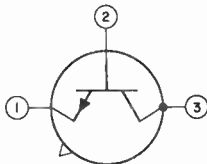
### GERMANIUM P-N-P DOUBLE-DIFFUSED-JUNCTION TYPE

For High-Speed Logic-Circuit Switching Applications in Commercial and Military Data-Processing Systems. The 2N955A is Unilaterally Interchangeable with Type 2N955.

#### GENERAL DATA

##### Mechanical:

Dimensions. . . . . See Outline TO-18 in General Section  
Terminal Diagram: BOTTOM VIEW



Lead 1 - Emitter  
Lead 2 - Base

Lead 3 - Collector,  
Case

#### SWITCHING SERVICE

Maximum and Minimum Ratings, Absolute-Maximum Values:

##### COLLECTOR-TO-BASE VOLTAGE:

With emitter open . . . . .  $V_{CB0}$  12 max. volts

##### COLLECTOR-TO-EMITTER VOLTAGE:

With base open. . . . .  $V_{CE0}$  8 max. volts

##### EMITTER-TO-BASE VOLTAGE:

With collector open . . . . .  $V_{EB0}$  2 max. volts

##### COLLECTOR CURRENT . . . . . $I_C$ 100 max. ma

##### TRANSISTOR DISSIPATION:<sup>a</sup>

At free-air temperature  
of 25° C or below . . . . . 150 max. mw

##### TEMPERATURE RANGE:

Junction (Operating). . . . .  $T_J$  -65 to +100 °C

Storage . . . . .  $T_{STG}$  -65 to +100 °C

##### LEAD TEMPERATURE:<sup>b</sup>

For 10 seconds maximum. . . . .  $T_L$  230 max. °C

<sup>a</sup> See accompanying Rating Chart.

<sup>b</sup> Measured 1/16" ± 1/32" along lead, down from seating plane.



# 2N955A

## ELECTRICAL CHARACTERISTICS

Free-air temperature = 25° C

Min. Typical Max.

DC Collector-to-Base Breakdown Voltage for dc collector ma. = 0.1, dc emitter current = 0.	$BV_{CBO}$	12	25	-	volts
DC Collector-to-Emitter Breakdown Voltage for dc collector ma. = 5, dc emitter current = 0.	$BV_{CEO}$	8	15	-	volts
DC Emitter-to-Base Breakdown Voltage for dc collector current = 0, dc emitter ma. = 0.1 . . . . .	$BV_{EBO}$	2	6	-	volts
DC Collector-to-Emitter Reach-Through Voltage for dc collector-to- base volts = 12, dc emitter-to-base float- ing potential (volts) = 1 . . . . .	$V_{RT}$	11	-	-	volts
DC Collector-to-Emitter Latching Voltage for dc collector ma. = 100, external base-to- emitter resistance (ohms) = 1000 . . . . .	$V_{CERL}^c$	9	-	-	volts
DC Base-to-Emitter Sat- uration Voltage for dc collector ma. = 30, dc base ma. = 1 . . . . .	$V_{BE}(sat)$	0.3	0.45	0.6	volt
DC Collector-to-Emitter Saturation Voltage: With dc collector ma. = 30, dc base ma. = 1 . . . . .	$V_{CE}(sat)$	-	0.22	0.3	volt
With dc collector ma. = 100, dc base ma. = 5 . . . . .		-	0.45	0.6	volt
DC Collector-Cutoff Current for dc col- lector volts = 5, dc emitter current = 0 . . . . .	$I_{CBO}$	-	0.6	5	$\mu a$
Input Capacitance for dc emitter-to-base volts = -0.5, dc col- lector current = 0, signal frequency (kc) = 100 . . . . .	$C_{ib}$	-	6	10	pf



# 2N955A

Output Capacitance for dc collector-to-base volts = 5, dc emitter current = 0, frequency (kc) = 100. . . . .	$C_{ob}$	-	4	6	pf
DC Forward-Current Transfer Ratio for dc collector-to-base volts = 0.3, dc collector ma. = 30 . . . .	$h_{FE}$	30	50	-	
Small-Signal Short-Circuit Forward Current Transfer Ratio for dc collector-to-emitter volts = 5, dc collector ma. = 20, signal frequency (Mc) = 100 . . .	$h_{fe}$	-	10	-	
Total Stored Charge for dc collector ma. = 30, dc base ma. = 1.5 . . .	$Q_s^d$	-	45	65	pc
Collector-to-Base Time Constant for dc collector supply volts = 3.5, dc collector-to-base volts = 3, dc emitter ma. = 10, frequency (Mc) = 31.9. . .	$r_b' C_c^e$	-	150	250	psec
Switching Time for dc collector supply volts = 5, dc collector ma. = 30: Delay time for dc base supply volts = -0.5, dc base-to-emitter volts = -0.5, turn-on dc base ma. = 4 . . . .	$t_d^f$	-	4.5	-	nsec
Rise time for dc base supply volts = -0.5, dc base-to-emitter volts = -0.5, turn-on dc base ma. = 4. . . . .	$t_r^f$	-	6.5	10	nsec
Storage time for dc base supply volts = 5, turn-on dc base ma. = 1.5, turn-off dc base ma. = -3. . . . .	$t_s^g$	-	5	-	nsec
Fall time for dc base supply volts = 5, turn-on dc base ma. = 1.5, turn-off dc base ma. = -3. . . . .	$t_f^g$	-	8	-	nsec



# 2N955A

Total turn-off time  
for dc base supply  
volts = 5, turn-on  
dc base ma. = 1.5,  
total stored charge  
(pf) = 65 . . . . .

$t_{Q_s}^d$  - 6 10 nsec

<sup>c</sup> See accompanying DC Collector-to-Emitter Latching-Voltage ( $V_{CERL}$ ) Measurement Circuit.

<sup>d</sup> See accompanying Total-Stored-Charge ( $Q_s$ ) and Total Turn-Off Time ( $t_{Q_s}$ ) Measurement Circuit.

<sup>e</sup> See accompanying Collector-to-Base Time-Constant Measurement Circuit.

<sup>f</sup> See accompanying Delay-Time ( $t_d$ ) and Rise-Time ( $t_r$ ) Measurement Circuit.

<sup>g</sup> See accompanying Storage-Time ( $t_s$ ) and Fall-Time ( $t_f$ ) Measurement Circuit.

## OPERATING CONSIDERATIONS

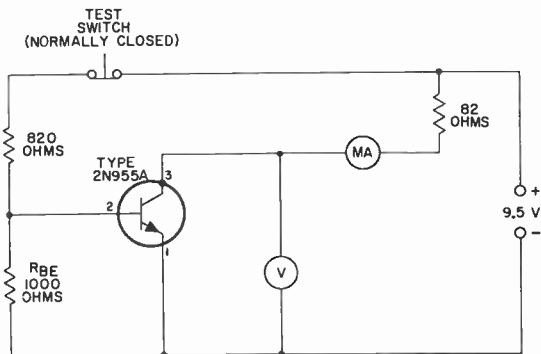
It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The flexible leads of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the seating plane provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the seals of the leads and damage the transistor.

It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.

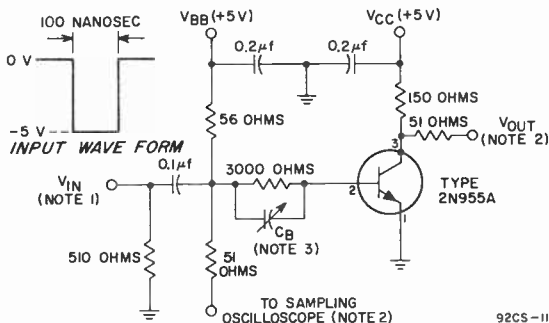


## DC COLLECTOR-TO-EMITTER LATCHING-VOLTAGE ( $V_{CERL}$ ) MEASUREMENT CIRCUIT



92CS-11398R1

## TOTAL-STORED-CHARGE ( $Q_s$ ) AND TOTAL TURN-OFF TIME ( $t_{Qs}$ ) MEASUREMENT CIRCUIT



92CS-11399R1

NOTE 1: FROM A PULSE GENERATOR HAVING  $R_g = 50$  OHMS AND  $t_r < 1$  NANOSECOND.

NOTE 2: SAMPLING OSCILLOSCOPE INPUT IMPEDANCE = 1 MEGOHM SHUNTED WITH 3 PICOFARADS,  $t_r = 0.35$  NANOSECOND.

NOTE 3: FOR MEASUREMENT OF  $Q_s$ ,  $C_B$  IS A CALIBRATED VARIABLE CAPACITOR HAVING A RANGE OF APPROXIMATELY 3.5 TO 35 PICOFARADS. FOR MEASUREMENT OF  $t_{Qs}$ ,  $C_B$  IS A FIXED CAPACITOR HAVING A VALUE OF:

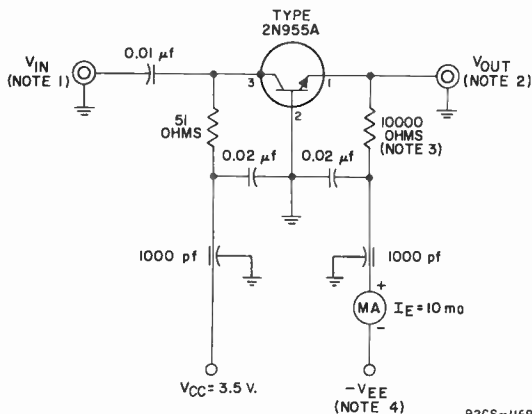
FOR 2N955A, 14 pf  $\pm$  2 PER CENT

FOR 2N955, 27 pf  $\pm$  2 PER CENT



# 2N955A

## COLLECTOR-TO-BASE TIME-CONSTANT ( $r_b'C_c$ ) MEASUREMENT CIRCUIT



92CS-11697

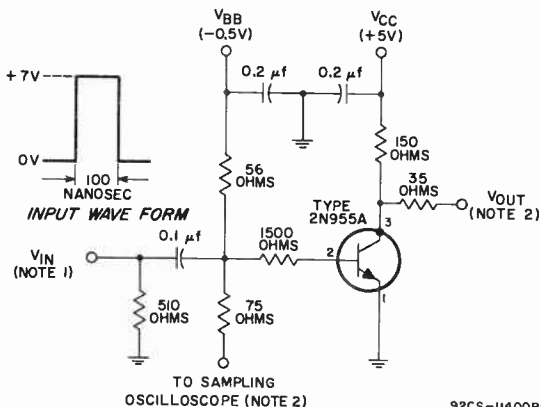
**NOTE 1:**  $V_{IN} = 0.5$  RMS VOLTS, FREQUENCY =  $31.9 \text{ Mc}$ , SIGNAL GENERATOR IMPEDANCE =  $50 \text{ OHMS}$ .

**NOTE 2:**  $V_{OUT}$  MEASURED WITH RF VOLTMETER,  $r_b'C_c = 10 V_{OUT}$ , WHERE  $r_b'C_c$  IS IN PICOSECONDS AND  $V_{OUT}$  IS IN MILLIVOLTS.

**NOTE 3:** HIGH-FREQUENCY TYPE.

**NOTE 4:** ADJUSTED FOR AN EMITTER CURRENT OF  $10$  MILLIAMPERES.

## DELAY-TIME ( $t_d$ ) AND RISE-TIME ( $t_r$ ) MEASUREMENT CIRCUIT



92CS-11400R1

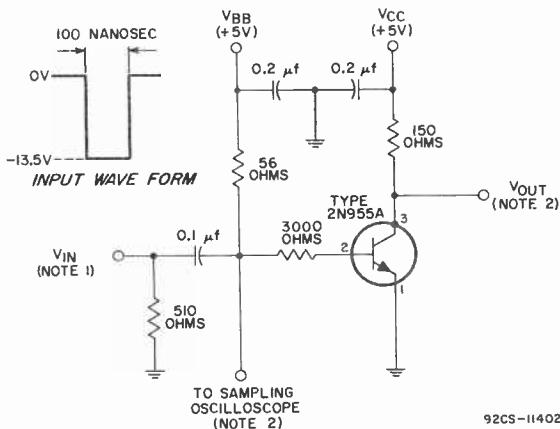




NOTE 1: FROM A PULSE GENERATOR HAVING  $R_g = 50$  OHMS AND  $t_r < 1$  NANOSECOND.

NOTE 2: SAMPLING OSCILLOSCOPE INPUT IMPEDANCE = 1 MEGOHM SHUNTED WITH 3 PICOFARADS,  $t_r = 0.35$  NANOSECOND.

## STORAGE-TIME ( $t_s$ ) AND FALL-TIME ( $t_f$ ) MEASUREMENT CIRCUIT



92CS-11402R1

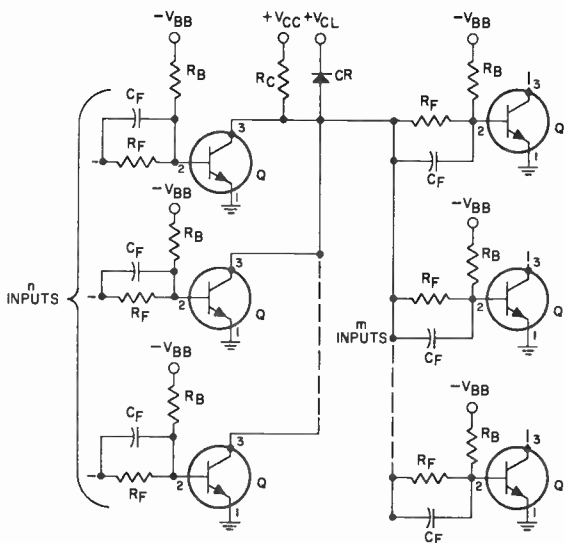
NOTE 1: FROM A PULSE GENERATOR HAVING  $R_g = 50$  OHMS AND  $t_r < 1$  NANOSECOND.

NOTE 2: SAMPLING OSCILLOSCOPE INPUT IMPEDANCE = 1 MEGOHM SHUNTED WITH 3 PICOFARADS,  $t_r = 0.35$  NANOSECOND.



# 2N955A

## RCTL CIRCUIT FOR MEASUREMENT OF PROPAGATION DELAY PER STAGE



92CS-11709R1

$$m = n = 5$$

$C_F = 27 \text{ pf}$

$R_B = 39000 \text{ ohms}$

$V_{BB} = 15 \text{ volts}$

$C_R = \text{Type IN955}$

$R_C = 510 \text{ ohms}$

$V_{CC} = 15 \text{ volts}$

$Q = \text{Type 2N955A}$

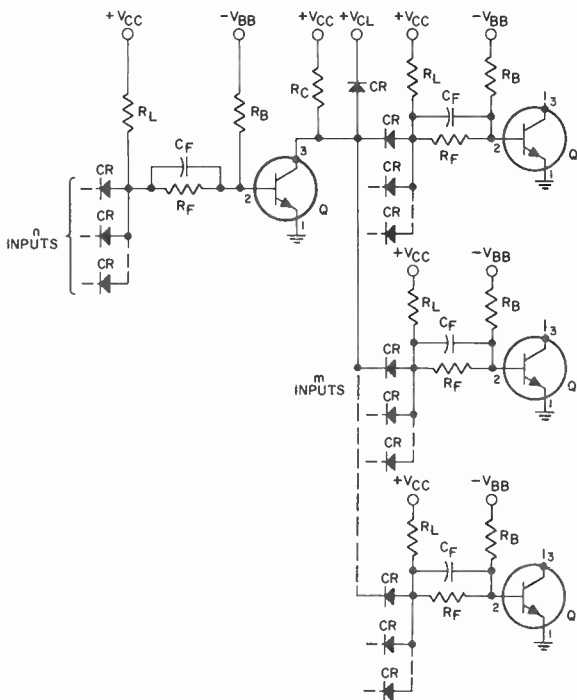
$R_F = 2000 \text{ ohms}$

$V_{CL} = 5 \text{ volts}$

NOTE: ALL CAPACITANCE, RESISTANCE, AND VOLTAGE VALUES HAVE  $\pm 5$  PER CENT TOLERANCE. OPERATING TEMPERATURE RANGE =  $0^\circ$  to  $55^\circ \text{ C}$ .

# 2N955A

## DTL CIRCUIT FOR MEASUREMENT OF PROPAGATION DELAY PER STAGE



92CS-11708RI

$$m = n = 4$$

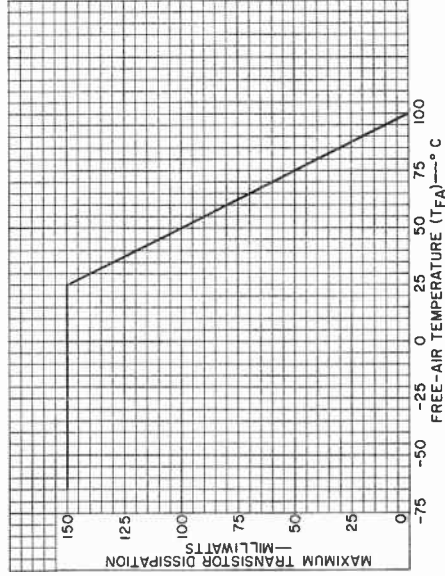
$C_F = 30 \text{ pf}$	$R_B = 24000 \text{ ohms}$	$V_{BB} = 15 \text{ volts}$
$C_R = \text{Type IN955}$	$R_C = R_L = 2000 \text{ ohms}$	$V_{CC} = 15 \text{ volts}$
$Q = \text{Type 2N955A}$	$R_F = 1800 \text{ ohms}$	$V_{CL} = 5 \text{ volts}$

NOTE: ALL CAPACITANCE, RESISTANCE, AND VOLTAGE VALUES HAVE  $\pm 5$  PER CENT TOLERANCE. OPERATING TEMPERATURE RANGE =  $0^\circ$  to  $55^\circ \text{ C.}$



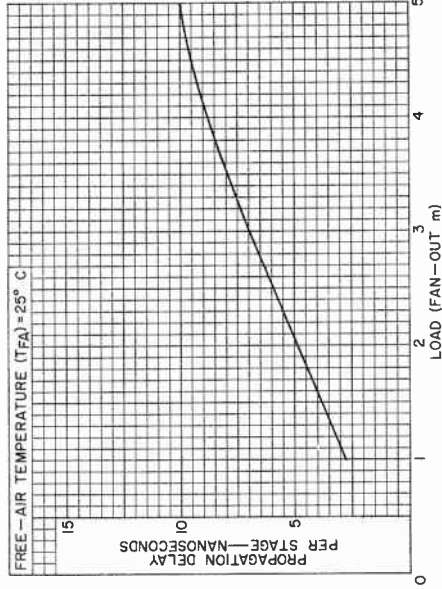
# 2N955A

## RATING CHART

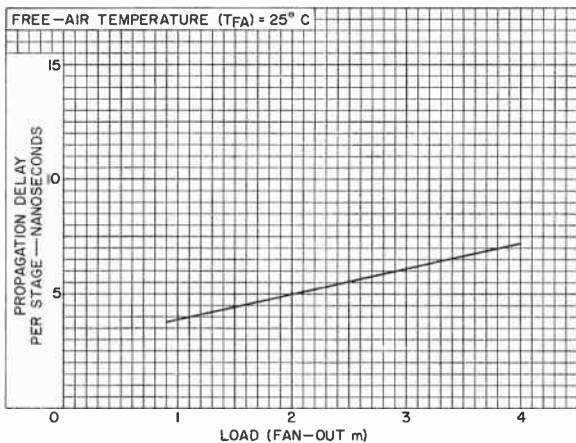


92CS-11404

## TYPICAL OPERATION CHARACTERISTIC IN ACCOMPANYING RCTL CIRCUIT



92CS-11712

TYPICAL OPERATION CHARACTERISTIC  
IN ACCOMPANYING DTL CIRCUIT

92CS-11711





## Power Transistor

## GERMANIUM P-N-P ALLOY TYPE

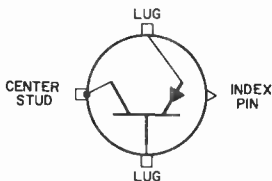
For Power Switching and Amplifier Service  
in Industrial and Military Applications

## GENERAL DATA

## Mechanical:

Operating Position . . . . .	Any
Maximum Seated Length . . . . .	0.520"
Maximum Diameter . . . . .	1.250"
Dimensional Outline . . . . .	JEDEC No. TO-36
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic
Terminal Diagram (See <i>Dimensional Outline</i> ):	

## BOTTOM VIEW



## INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter, chopper,  
voltage- and current-regulator, dc- and audio  
amplifier, relay- and solenoid-actuating circuits

## Maximum and Minimum Ratings, Absolute Maximum Values:

## COLLECTOR-TO-BASE VOLTAGE:

With emitter-to-base reverse biased

(DC emitter-to-base volts = -1.5) . . . . .	-80 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-40 max.	volts
COLLECTOR CURRENT . . . . .	-15 max.	amp
EMITTER CURRENT . . . . .	15 max.	amp
BASE CURRENT . . . . .	-4 max.	amp

TRANSISTOR DISSIPATION:<sup>a</sup>

At case temperatures<sup>b</sup> of 25° C or below . . . . . 150 max. watts

CASE-TEMPERATURE<sup>b</sup> RANGE:

Operating and storage . . . . . -65 to +100 °C

## Typical Operation:

In a common emitter, base-input, power-switching  
circuit at case temperature<sup>b</sup> of 25° C

DC Supply Voltage . . . . .	-12	volts
DC Base-Bias Voltage . . . . .	6	volts
"On" DC Collector Current . . . . .	-12	amp
"Turn-On" Base Current . . . . .	-2	amp
"Turn-Off" Base Current . . . . .	0	amp

← indicates a change.



# 2N1099

## Switching Time:

Rise time. . . . .	15	$\mu$ sec
Fall time. . . . .	15	$\mu$ sec

<sup>a</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

<sup>b</sup> Measured at any point on seating surface.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and at case temperature<sup>b</sup> of 25°C unless otherwise specified

Min. Typical Max.

DC Collector-to-Emitter Breakdown Voltage:						
With base connected to emitter, dc collector amperes =						
-0.3 . . . . .	$BV_{CES}$	-70	-	-	-	volts
With base open:						
For dc collector amperes = -0.3 . . . . .						
	$BV_{CEO}$	-	-60	-	-	volts
For dc collector amperes = -1 <sup>c</sup> . . . . .						
		-55	-	-	-	volts
DC Base-to-Emitter Voltage for dc collector-to-emitter volts = -2, dc collector amperes = -5. . . . .						
	$V_{BE}$	-	-0.65	-0.9	-	volt
DC Collector-to-Emitter Saturation Voltage for dc collector amperes = -12, dc base amperes = -2 . . . . .						
	$V_{CE}$	-	-0.3	-0.7	-	volt
DC Emitter Voltage for (sat) dc collector volts = -80, dc emitter current = 0. . . . .						
	$V_{EB}$	-	-0.15	-1	-	volt
DC Punch-Through Voltage. . . . .						
	$V_{PT}$	-80	-	-	-	volts
DC Emitter-Cutoff Current for dc emitter volts = -40, dc collector current = 0 . . . . .						
	$I_{EBO}$	-	-1	-4	-	ma
DC Collector-Cutoff Current:						
With dc collector volts = -2, dc emitter current = 0. . . . .						
	$I_{CBO}$	-	100	-	-	$\mu$ a
With dc collector volts = -80, dc emitter current = 0. . . . .						
		-	-2	-4	-	ma

→ Indicates a change.





With dc collector volts = -80, dc emitter current = 0, case temperature <sup>b</sup> = 71° C. . . . .		-	-	-15	ma
DC Current Transfer Ratio for dc col- lector-to-emitter volts = -2, dc collector amperes = -5 . . . . .	$h_{FE}$			35	70
-12 . . . . .			25	-	
Beta-Cutoff Frequency for dc collector-to- emitter volts = -6, dc collector amperes = -5 . . . . .	$f_{ae}$		10	-	kc
Thermal Resistance: Junction-to-case . . .	$R_T$		0.35	0.5	°C/watt
Thermal Capacity for pulse duration of 1 to 10 milliseconds. . . .			0.075	-	watt- sec/°C msec
Thermal Time Constant. .	$\tau_1$		26.25	-	msec

<sup>b</sup> Measured at any point on seating surface.

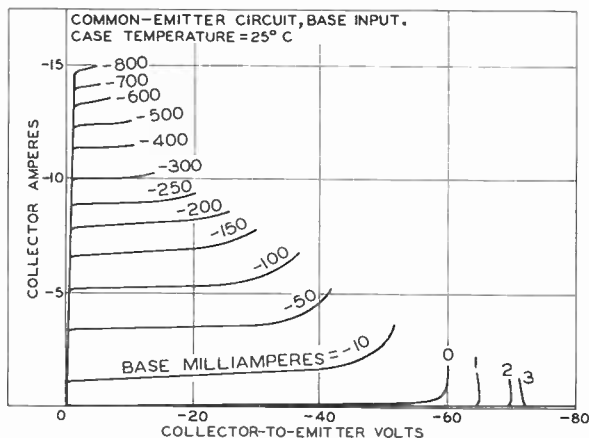
<sup>c</sup> Tested by sweep method to prevent excessive heating of collector junction.

PERFORMANCE TESTS,  
 OPERATING CONSIDERATIONS,  
 DIMENSIONAL OUTLINE,  
 SUGGESTED MOUNTING ARRANGEMENT,  
 RATING CHART,  
 TYPICAL BASE-CHARACTERISTICS CURVES,  
 and  
 TYPICAL CHARACTERISTICS CURVES  
 shown under Type 2N173 also apply to the 2N1099

← Indicates a change.



## TYPICAL COLLECTOR CHARACTERISTICS



92CS-10733

## Power Transistor

## GERMANIUM P-N-P ALLOY TYPE

For Power Switching and Amplifier Service  
in Industrial and Military Applications

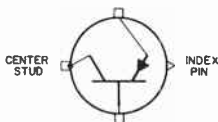
## GENERAL DATA

## Mechanical:

Operating Position . . . . .	Any
Maximum Overall Length . . . . .	1.230"
Maximum Seated Length . . . . .	0.520"
Maximum Diameter . . . . .	1.250"
Dimensional Outline . . . . .	JEDEC No. TO-36
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic

Terminal Diagram (See Dimensional Outline):

## BOTTOM VIEW



## INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter, chopper,  
voltage- and current-regulator, dc- and audio  
amplifier, relay- and solenoid-actuating circuits

Maximum and Minimum Ratings, Absolute Maximum Values:

## COLLECTOR-TO-BASE VOLTAGE:

With emitter-to-base reverse biased

(DC emitter-to-base volts = -1.5) . . . . .

EMITTER-TO-BASE VOLTAGE . . . . . -40 max. volts

COLLECTOR CURRENT . . . . . -15 max. amp

EMITTER CURRENT . . . . . 15 max. amp

BASE CURRENT . . . . . -4 max. amp

TRANSISTOR DISSIPATION:  $\Delta$ 

At case temperature of 25° C. . . . . 87.5 max. watts

## CASE-TEMPERATURE RANGE:

Continuous operation . . . . . -65 to +95 °C

Intermittent operation . . . . . -65 to +100 °C

Storage . . . . . -65 to +100 °C

## Typical Operation:

In a common emitter, base-input, power-switching  
circuit at case temperature of 25° C

DC Supply Voltage . . . . . -12 volts

DC Base-Bias Voltage . . . . . 6 volts

"On" DC Collector Current . . . . . -12 amp

"Turn-On" Base Current . . . . . -2 amp

"Turn-Off" Base Current . . . . . 0 amp



# 2N1099

## Switching Time:

Rise time. . . . .	15	$\mu$ SEC
Fall time. . . . .	15	$\mu$ SEC

▲ See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and case temperature of 25° C unless otherwise specified

Min. Typical Max.

### DC Collector-to-Emitter

#### Breakdown Voltage:

With base connected to emitter, dc collector amperes =

-0.3 . . . . .  $BV_{CES}$  -70 - - volts

With base open:

For dc collector amperes = -0.3 . . . . .  $BV_{CEO}$  - -60 - volts

For dc collector amperes = -1 . . . . . -55 - - volts

### DC Base-to-Emitter

Voltage\* for dc collector-to-emitter

volts = -2, dc collector amperes = -5. . . . .  $V_{BE}$  - -0.65 -0.9 volt

### DC Collector-to-Emitter

Saturation Voltage\*

for dc collector amperes = -12, base amperes = -2 . . . . .  $V_{CE}$  - -0.3 -0.7 volt

### DC Emitter Voltage for

dc collector volts =

-80, dc emitter amperes = 0. . . . .  $V_{EB}$  - -0.15 -1 volt

### DC Punch-Through

Voltage. . . . .  $V_P$  -80 - - volts

### DC Emitter-Cutoff

Current for dc emitter

volts = -40, dc collector amperes = 0 . . . . .  $I_{EBO}$  - -1 -8 ma

### DC Collector-Cutoff

Current:

With dc collector volts = -2, dc emitter amperes = 0. . . . .  $I_{CBO}$  - 100 -  $\mu$ a

With dc collector

volts = -80, dc emitter amperes = 0. . . . . - -2 -8 ma



With dc collector volts = -80, dc emitter amperes = 0, case temperature = 71° C. . . . .		-	-	-15	ma
DC Current Transfer Ratio* for dc col- lector-to-emitter volts = -2, dc collector amperes = -5 . . . . .	$h_{FE}$	35	-	70	
-12 . . . . .		-	25	-	
Beta-Cutoff Frequency* for dc collector-to- emitter volts = -6, dc collector amperes = -5 . . . . .	$f_{ae}$	-	10	-	kc
Thermal Resistance: Junction-to-case . . .	$R_T$	-	0.5	0.8	°C/watt
Thermal Capacity for pulse duration of 1 to 10 milliseconds. . . .		-	0.075	-	watt- sec/°C
Thermal Time Constant. . .	$\tau_1$	-	37.5	-	msec

• Sweep voltage used to perform test.

\* Measured in a common-emitter, base-input circuit.

### OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

Electrical connection can be made to the base and emitter terminals by means of clips or by soldering directly to the terminals. When soldering connections are made to the terminals, care should be taken to conduct excessive heat away from the terminal seals, otherwise the heat of the soldering operation will crack the glass seals of the terminals and damage the transistor.

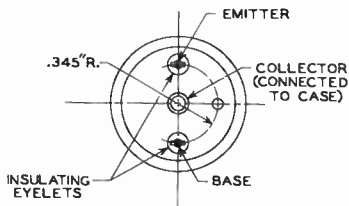
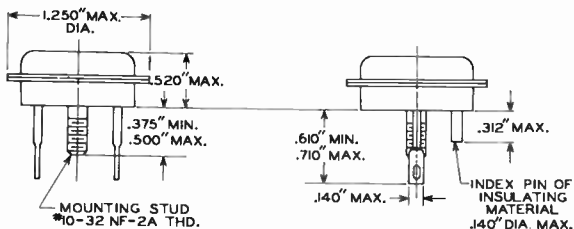
This transistor is provided with a single-ended stud for mounting to a heat sink and for electrical connection to the collector. (See accompanying *Suggested Mounting Arrangement*). Electrical connection to the base and to the emitter is made to their respective terminals.

It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.

The maximum torque on mounting stud should not exceed 12 inch-pounds.

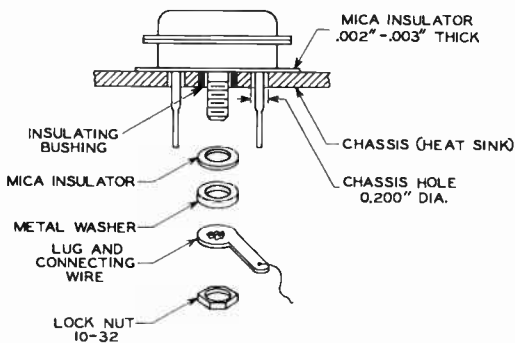


# 2N1099



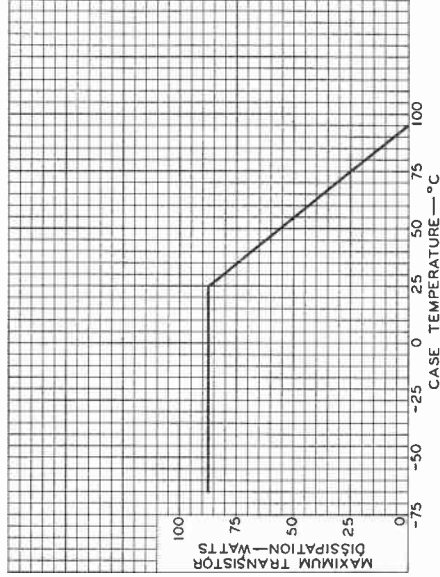
92CM-10612RI

## SUGGESTED MOUNTING ARRANGEMENT



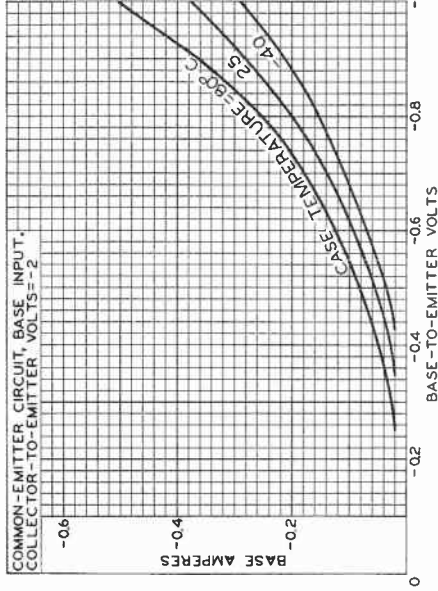
92CS-10624RI

## RATING CHART



92CS-10702

## TYPICAL BASE CHARACTERISTICS

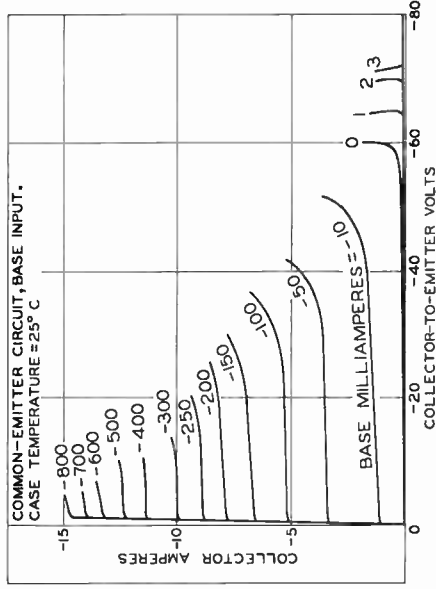


92CS-10703



# 2N1099

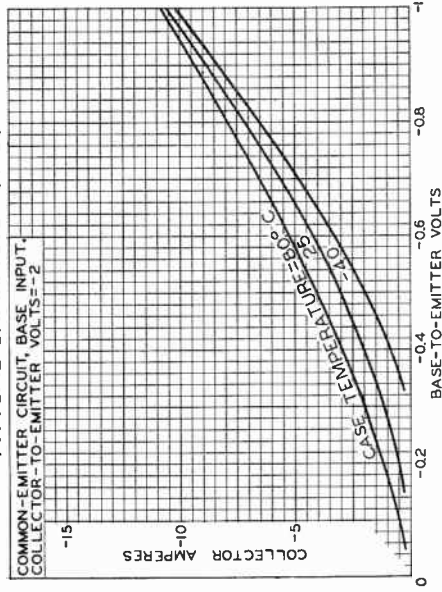
## TYPICAL COLLECTOR CHARACTERISTICS



92CS-10733

World Radio History

## TYPICAL CHARACTERISTICS



92CS-10709

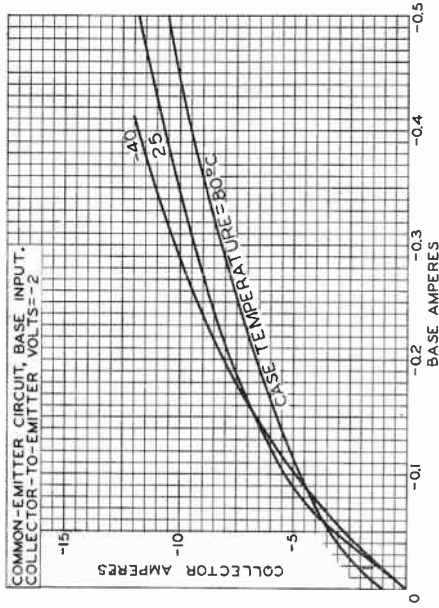
RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division



Somerville, N. J.



## TYPICAL CHARACTERISTICS





## Power Transistor

## GERMANIUM P-N-P ALLOY TYPE

For Power Switching and Amplifier Service  
in Industrial and Military Applications

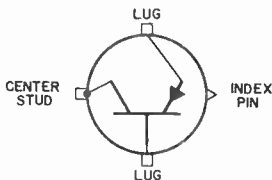
## GENERAL DATA

## Mechanical:

Operating Position . . . . .	Any
Maximum Seated Length . . . . .	0.520"
Maximum Diameter . . . . .	1.250"
Dimensional Outline . . . . .	JEDEC No. TO-36
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic

Terminal Diagram (See *Dimensional Outline*):

BOTTOM VIEW



## INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter, chopper,  
voltage- and current-regulator, dc- and audio-  
amplifier, relay- and solenoid-actuating circuits

## Maximum and Minimum Ratings, Absolute-Maximum Values:

## COLLECTOR-TO-BASE VOLTAGE:

With emitter-to-base reverse biased

(DC emitter-to-base volts = -1.5) . . . . .	-100 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-80 max.	volts
COLLECTOR CURRENT . . . . .	-15 max.	amp
EMITTER CURRENT . . . . .	15 max.	amp
BASE CURRENT . . . . .	-4 max.	amp

TRANSISTOR DISSIPATION:<sup>a</sup>

At case temperature<sup>b</sup> of 25° C or below. . . . . 150 max. watts ←

CASE-TEMPERATURE<sup>b</sup> RANGE:

Operating and storage . . . . . -65 to +100 °C ←

## Typical Operation:

In a common-emitter, base-input, power-switching  
circuit at case temperature<sup>b</sup> of 25° C

DC Supply Voltage . . . . .	-12	volts
DC Base-Bias Voltage . . . . .	6	volts
"On" DC Collector Current . . . . .	-12	amp
"Turn-On" Base Current . . . . .	-2	amp
"Turn-Off" Base Current . . . . .	0	amp

← Indicates a change.



# 2N1100

## Switching Time:

Rise time . . . . .	15	$\mu$ sec
Fall time . . . . .	15	$\mu$ sec

<sup>a</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

<sup>b</sup> Measured at any point on seating surface.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and at case temperature<sup>b</sup> of 25° C unless otherwise specified

Min. Typical Max.

DC Collector-to-Emitter Breakdown Voltage:					
With base connected to emitter, dc collector amperes = -0.3 . . . . .	$BV_{CES}$	-80	-	-	volts
With base open:					
For dc collector amperes = -1 <sup>c</sup> . . . . .	$BV_{CEO}$	-65	-	-	volts
DC Base-to-Emitter Voltage for dc collector-to-emitter volts = -2, dc collector amperes = -5 . . . . .	$V_{BE}$	-	-0.65	-0.9	volt
DC Collector-to-Emitter Saturation Voltage for dc collector amperes = -12, dc base amperes = -2 . . . . .	$V_{CE(sat)}$	-	-0.3	-0.7	volt
DC Emitter Voltage for dc collector volts = -100, dc emitter current = 0 . . . . .	$V_{EB}$	-	-	-1	volt
DC Punch-Through Voltage . . . . .	$V_{PT}$	-100	-	-	volts
DC Emitter-Cutoff Current for dc emitter volts = -80, dc collector current = 0 . . . . .	$I_{EBO}$	-	-1	-4	ma
DC Collector-Cutoff Current:	$I_{CBO}$				
With dc collector volts = -2, dc emitter current = 0 . . . . .		-	100	-	$\mu$ a
With dc collector volts = -100, dc emitter current = 0 . . . . .		-	-2	-4	ma
With dc collector volts = -100, dc emitter current = 0, case temperature <sup>b</sup> = 71° C.		-	-	-15	ma

→ Indicates a change.



DC Current Transfer Ratio for dc collector-to-emitter volts = -2, dc collector amperes =	$h_{FE}$				
-5 . . . . .		25	-	50	
-12 . . . . .		-	20	-	
Beta-Cutoff Frequency for dc collector-to-emitter volts = -6, dc collector amperes = -5 . . . . .	$f_{ae}$	-	10	-	kc
Thermal Resistance: Junction-to-case . . . . .	$R_T$	-	0.35	0.5	$^{\circ}\text{C}/\text{watt}$
Thermal Capacity for pulse duration of 1 to 10 milliseconds . . . . .		-	0.075	-	$\frac{\text{watt-sec}}{^{\circ}\text{C}}$
Thermal Time Constant . . . . .	$\tau_1$	-	26.25	-	msec

<sup>b</sup> Measured at any point on seating surface.

<sup>c</sup> Tested by sweep method to prevent excessive heating of collector junction.

### PERFORMANCE TESTS

This transistor type is designed to pass the environmental tests specified in Military Specification MIL-S-19500B.

### OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

Electrical connection can be made to the base and emitter lugs by means of clips or by soldering directly to the lugs. When soldering connections are made to the lugs, care should be taken to conduct excessive heat away from the lug seals, otherwise the heat of the soldering operation will crack the glass seals of the lugs and damage the transistor.

This transistor is provided with a single-ended stud for mounting to a heat sink and for electrical connection to the collector. (See accompanying *Suggested Mounting Arrangement*). Electrical connection to the base and to the emitter is made to their respective lugs.

It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.

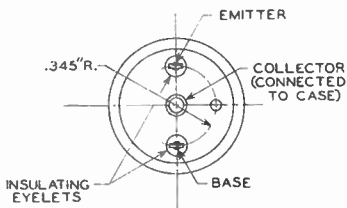
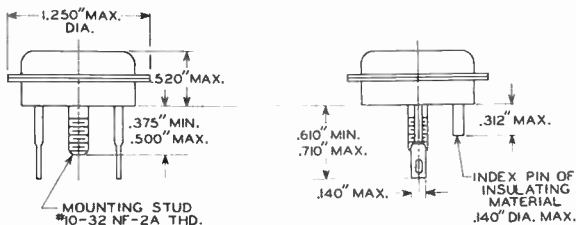
The maximum torque on mounting stud should not exceed 12 inch-pounds.

← indicates a change.



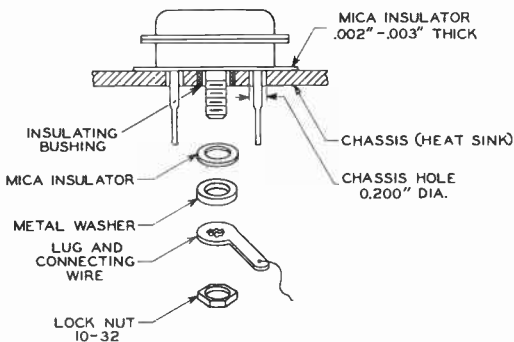
# 2N1100

JEDEC No. T0-36



92CM-10612RI

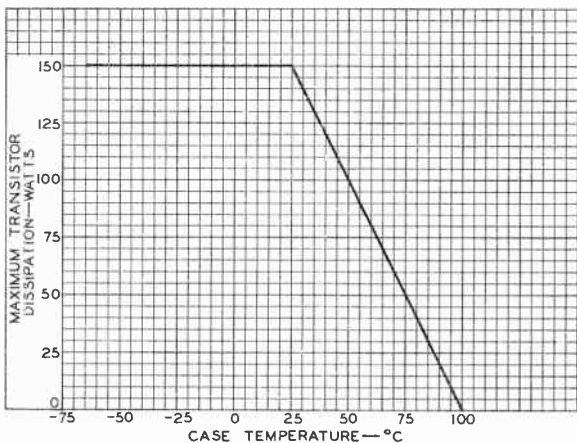
## SUGGESTED MOUNTING ARRANGEMENT



92CS-10624RI

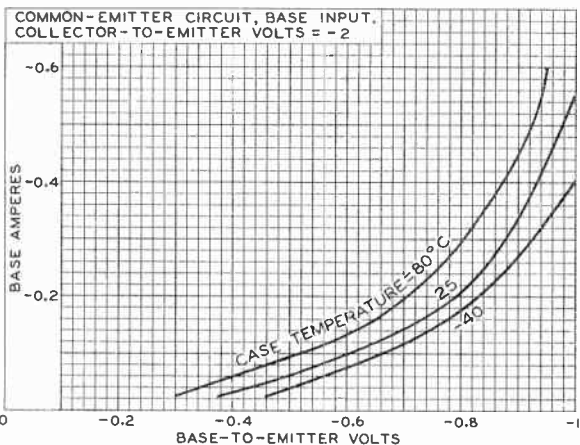


## RATING CHART



92CS-10702RI

## TYPICAL BASE CHARACTERISTICS

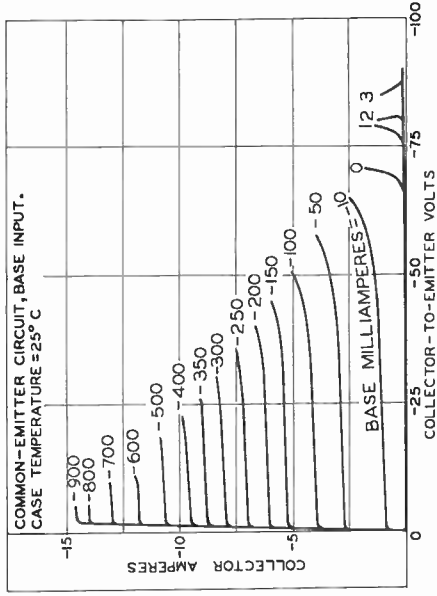


92CS-10706



# 2N1100

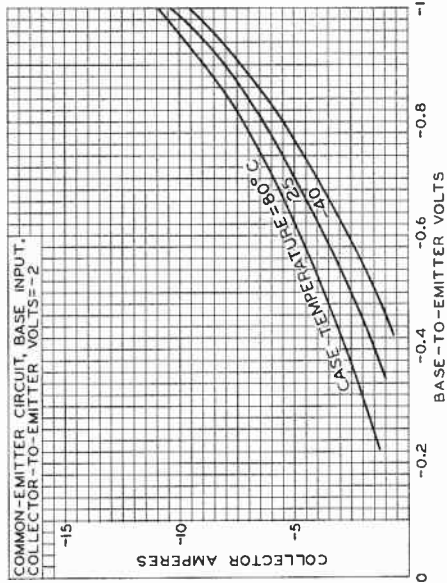
## TYPICAL COLLECTOR CHARACTERISTICS



World Radio History

92CS-10724

## TYPICAL CHARACTERISTICS



92CS-10710

Semiconductor & Materials Division

Somerville, N. J.



RADIO CORPORATION OF AMERICA



## Power Transistor

## GERMANIUM P-N-P ALLOY TYPE

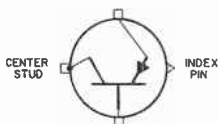
For Power Switching and Amplifier Service  
in Industrial and Military Applications

## GENERAL DATA

## Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	1.230"
Maximum Seated Length. . . . .	0.520"
Maximum Diameter. . . . .	1.250"
Dimensional Outline. . . . .	JEDEC No. TO-36
Case. . . . .	Welded, Metal
Seals. . . . .	Hermetic
Terminal Diagram (See <i>Dimensional Outline</i> ):	

## BOTTOM VIEW



## INDUSTRIAL SERVICE

*Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and audio amplifier, relay- and solenoid-actuating circuits*

## Maximum and Minimum Ratings, Absolute-Maximum Values:

## COLLECTOR-TO-BASE VOLTAGE:

With emitter-to-base reverse biased

(DC emitter-to-base volts = -1.5) . . . . . -100 max. volts

EMITTER-TO-BASE VOLTAGE . . . . . -80 max. volts

COLLECTOR CURRENT . . . . . -15 max. amp

EMITTER CURRENT . . . . . 15 max. amp

BASE CURRENT. . . . . -4 max. amp

TRANSISTOR DISSIPATION:<sup>A</sup>

At case temperature of 25° C. . . . . 87.5 max. watts

## CASE-TEMPERATURE RANGE:

Continuous operation. . . . . -65 to +95 °C

Intermittent operation. . . . . -65 to +100 °C

Storage . . . . . -65 to +100 °C

## Typical Operation:

*In a common-emitter, base-input, power-switching circuit at case temperature of 25° C*

DC Supply Voltage . . . . . -12 volts

DC Base-Bias Voltage. . . . . 6 volts

"On" DC Collector Current . . . . . -12 amp

"Turn-On" Base Current. . . . . -2 amp

"Turn-Off" Base Current . . . . . 0 amp



# 2N1100

## Switching Time:

Rise time . . . . .	15	$\mu$ sec
Fall time . . . . .	15	$\mu$ sec

▲ See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and case temperature of 25° C unless otherwise specified

Min. Typical Max.

DC Collector-to-Emitter Breakdown Voltage:					
With base connected to emitter, dc collector amperes = -0.3 . . . . .	$BV_{CES}$	-80	-	-	volts
With base open:					
For dc collector amperes = -1 . . . . .	$BV_{CEO}$	-65	-	-	volts
DC Base-to-Emitter Voltage* for dc collector-to-emitter volts = -2, dc collector amperes = -5 . . . . .	$V_{BE}$	-	-0.65	-0.9	volt
DC Collector-to-Emitter Saturation Voltage* for dc collector amperes = -12, base amperes = -2 . . . . .	$V_{CE}$	-	-0.3	-0.7	volt
DC Emitter Voltage for dc collector volts = -100, dc emitter amperes = 0 . . . . .	$V_{EB}$	-	-	-1	volt
DC Punch-Through Voltage . . . . .	$V_P$	-100	-	-	volts
DC Emitter-Cutoff Current for dc emitter volts = -80, dc collector amperes = 0 . . . . .	$I_{EBO}$	-	-1	-8	ma
DC Collector-Cutoff Current:	$I_{CBO}$				
With dc collector volts = -2, dc emitter amperes = 0 . . . . .		-	100	-	$\mu$ a
With dc collector volts = -100, dc emitter amperes = 0 . . . . .		-	-2	-8	ma
With dc collector volts = -100, dc emitter amperes = 0, case temperature = 71° C . . . . .		-	-	-15	ma



DC Current Transfer Ratio* $h_{FE}$				
for dc collector-to-emitter volts = -2, dc collector amperes =				
-5 . . . . .	25	-	50	
-12 . . . . .	-	20	-	
Beta-Cutoff Frequency* for dc collector-to-emitter volts = -6, dc collector amperes = -5 . . . $f_{ae}$	-	10	-	kc
Thermal Resistance:				
Junction-to-case . . . . . $R_T$	-	0.5	0.8	$^{\circ}\text{C}/\text{watt}$
Thermal Capacity for pulse duration of 1 to 10 milliseconds . . . . .	-	0.075	-	$\frac{\text{watt-sec}}{^{\circ}\text{C}}$ msec
Thermal Time Constant . . . $\tau_1$	-	37.5	-	msec

• Sweep voltage used to perform test.

★ Measured in a common-emitter, base-input circuit.

### OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

Electrical connection can be made to the base and emitter terminals by means of clips or by soldering directly to the terminals. When soldering connections are made to the terminals, care should be taken to conduct excessive heat away from the terminal seals, otherwise the heat of the soldering operation will crack the glass seals of the terminals and damage the transistor.

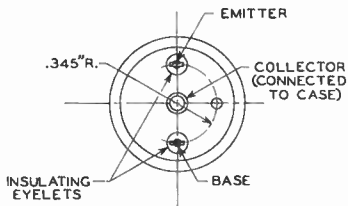
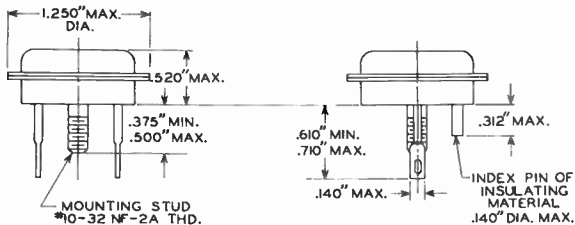
This transistor is provided with a single-ended stud for mounting to a heat sink and for electrical connection to the collector. (See accompanying *Suggested Mounting Arrangement*). Electrical connection to the base and to the emitter is made to their respective terminals.

It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.

The maximum torque on mounting stud should not exceed 12 inch-pounds.

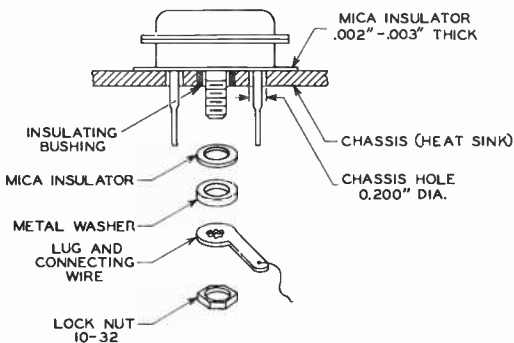


# 2N1100



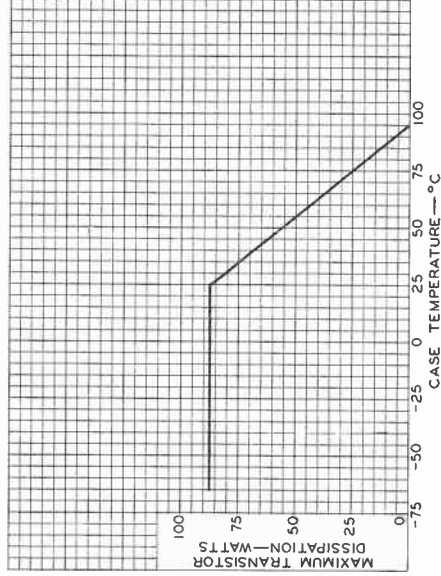
92CM-10612R1

## SUGGESTED MOUNTING ARRANGEMENT



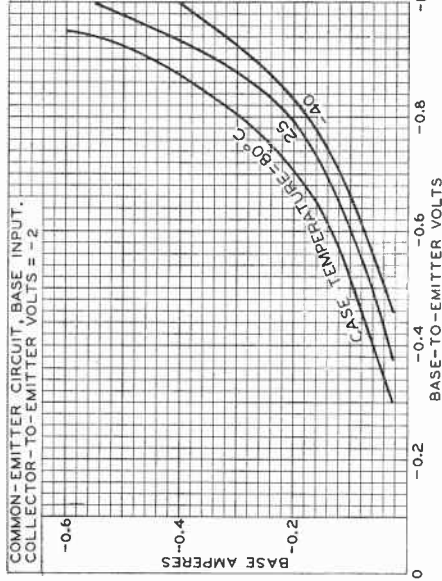
92CS-10624R1

## RATING CHART



92CS-10702

## TYPICAL BASE CHARACTERISTICS

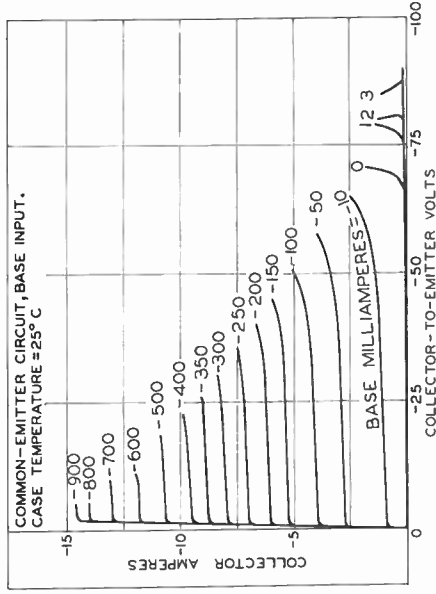


92CS-10706



# 2N1100

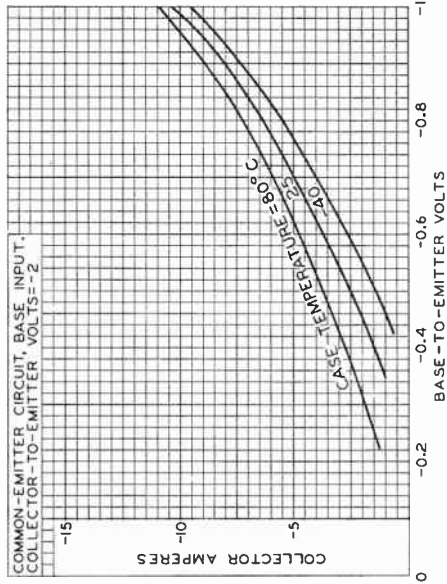
## TYPICAL COLLECTOR CHARACTERISTICS



92CS-10724

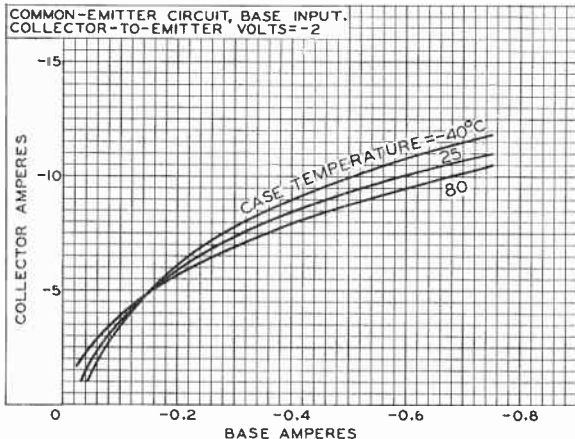
World Radio History

## TYPICAL CHARACTERISTICS



92CS-10710

## TYPICAL CHARACTERISTICS



92CS-10711







# Bidirectional Transistor

## GERMANIUM N-P-N ALLOY TYPE

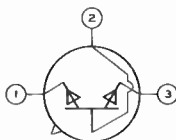
For Medium-Speed Switching Service in Industrial and Military Data-Processing Systems

### GENERAL DATA

#### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter . . . . .	0.370"
Dimensional Outline . . . . .	JEDEC No. TO-5
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter  
(Or Collector)  
Lead 2 - Base



Lead 3 - Collector  
(Or Emitter)

### SWITCHING SERVICE

*Such as in bidirectional switching, core-driver, and ac-signal-relay circuits*

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	25 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	25 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
Base-to-emitter volts = -1 . . . . .	20 max.	volts
Base open . . . . .	18 max.	volts
COLLECTOR CURRENT . . . . .	±400 max.	ma
EMITTER CURRENT . . . . .	±400 max.	ma
TRANSISTOR DISSIPATION: <sup>▲</sup>		
At ambient temperature of 25° C . . . . .	120 max.	mw
At ambient temperature of 55° C . . . . .	35 max.	mw
At ambient temperature of 71° C . . . . .	10 max.	mw
AMBIENT TEMPERATURE (During operation) . . . . .	71 max.	°C
STORAGE-TEMPERATURE RANGE . . . . .	-65 to +85	°C

#### Typical Operation:

*In accompanying typical inverter circuit at ambient temperature of 25° C*

"On" Collector Current . . . . .	200	ma
"Turn-On" Base Current ( $I_{B1}$ ) . . . . .	20	ma
"Turn-Off" Base Current ( $I_{B2}$ ) . . . . .	-20	ma



# 2N1169

## Switching Time:

Delay time ( $t_d$ ) . . . . .	0.05	$\mu$ sec
Rise time ( $t_r$ ) . . . . .	0.35	$\mu$ sec
Storage time ( $t_s$ ) . . . . .	0.45	$\mu$ sec
Fall time ( $t_f$ ) . . . . .	0.2	$\mu$ sec

▲ See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## CHARACTERISTICS RANGE VALUES FOR EQUIPMENT DESIGN

Voltage values are given with respect to the case unless otherwise specified. Ambient temperature of 25° C.

	Min.	Typical	Max.	
DC Collector Breakdown				
Voltage for dc collector $\mu$ a = -50, emitter open. . . . .	$BV_{CBO}$	25	35	- volts
DC Punch-Through				
Voltage for dc emitter volts = 1 . . . . .	$V_P$	20	35	- volts
DC Base-to-Emitter				
Voltage for dc collector ma. = 200, dc base ma. = 10 . . . . .	$V_{BE}$	-	1	1.5 volts
DC Collector-to-Emitter				
Saturation Voltage for dc collector ma. = 200, dc base ma. = 10. . . . .	$V_{CE}$	-	0.1	0.3 volt
DC Collector-Cutoff				
Current for dc collector volts = 12, emitter open. . . . .	$I_{CBO}$	-	3	10 $\mu$ a
DC Current Transfer				
Ratio for dc collector-to-emitter volts = 0.3, dc collector ma. = 200 . . . . .	$h_{FE}$	20	40	-
Alpha-Cutoff Frequency				
for dc collector volts = 6, dc collector ma. = 1 . . . . .	$f_{\alpha b}$	4.5	7	- Mc
Collector-to-Base Capacitance for dc collector volts = 6, dc collector ma. = 0. . . . .	$C_{ob}$	-	19	- $\mu$ mf
Thermal Time Constant . . . . .	$\tau_1$	-	12	- msec
Thermal Resistance between collector junction and free air . . . . .	$R_T$	-	-	500 °C/watt



## OPERATING CONSIDERATIONS

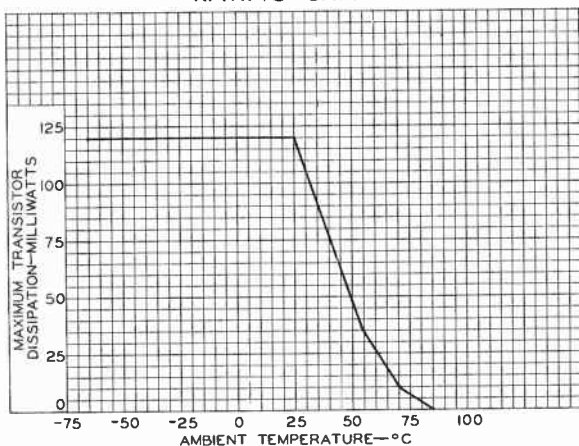
It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using this transistor, the temperature of the solder should not exceed  $255^{\circ}\text{C}$  for a maximum immersion period of 10 seconds.

This transistor is intended for use in single-side printed circuit boards and in conventional wire-in type circuits. If this transistor is used in double-side printed-circuit boards or in printed-circuit boards utilizing eyelets, it may be necessary to use an insulating washer or similar standoff device made of good dielectric material to prevent the solder from shorting the leads to each other or to the board.

## RATING CHART

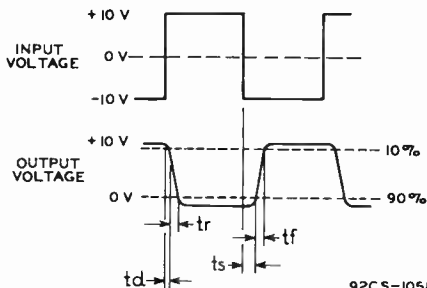
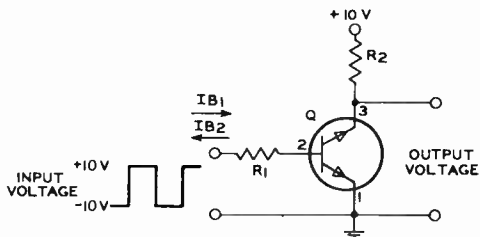


92CS-10573R1



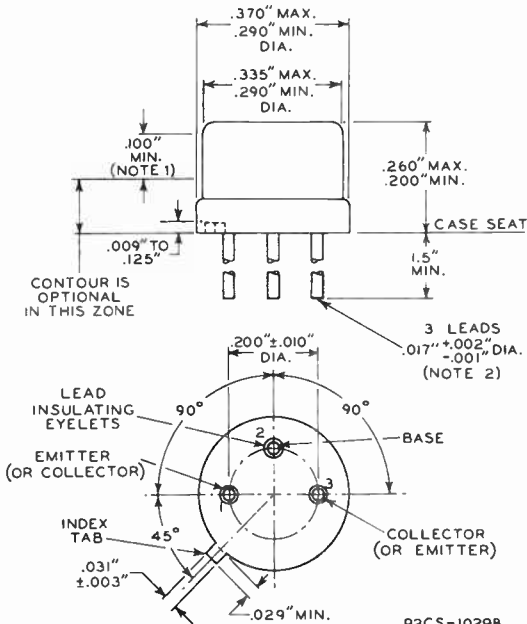
# 2N1169

## TYPICAL INVERTER CIRCUIT AND ASSOCIATED WAVE FORMS



92CS-10589

- Q: Transistor type 2N1169
- R<sub>1</sub>: 500 ohms, 0.5 watt
- R<sub>2</sub>: 50 ohms, 0.5 watt

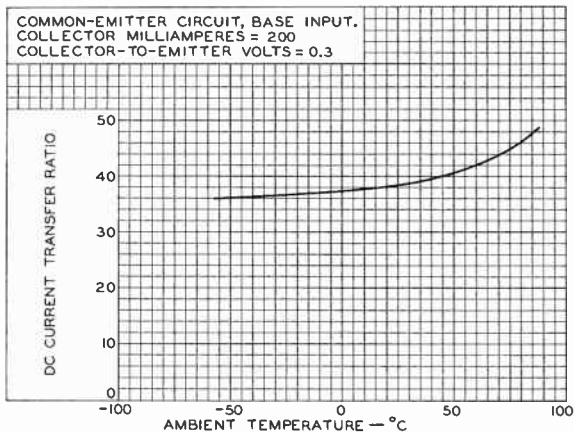


NOTE 1: THE DIAMETER IN THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE TOTAL VARIATION IN ACTUAL DIAMETER FROM THE TRUE DIAMETER, DUE TO TAPER AND OUT OF ROUND WITHIN THIS ZONE, WILL NOT EXCEED  $0.010''$ .

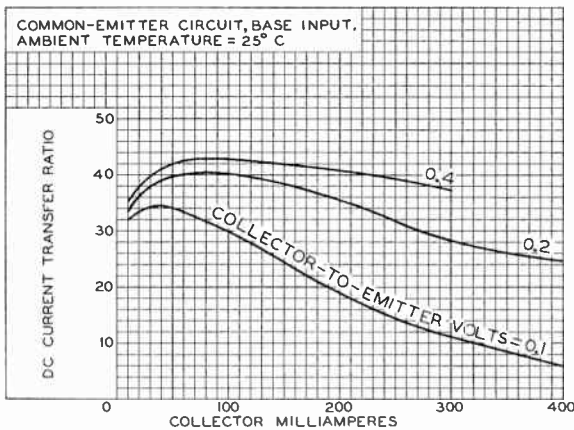
NOTE 2: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN  $0.05''$  AND  $0.25''$  FROM THE CASE SEAT. BETWEEN  $0.25''$  AND  $1.5''$ , A MAXIMUM DIAMETER OF  $0.021''$  IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.



## TYPICAL OPERATION CHARACTERISTICS



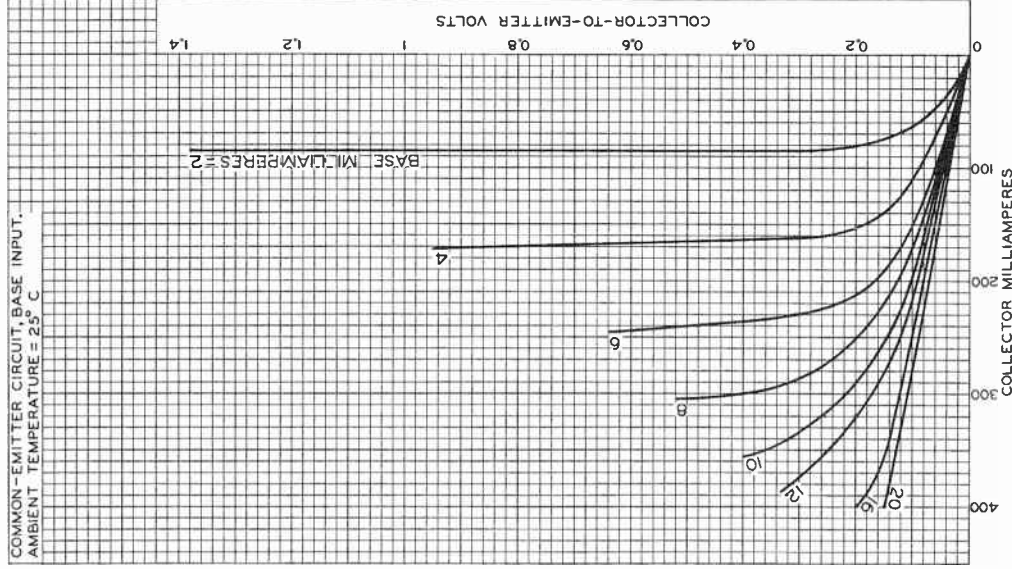
92CS-10293



92CS-10287

## TYPICAL COLLECTOR CHARACTERISTICS

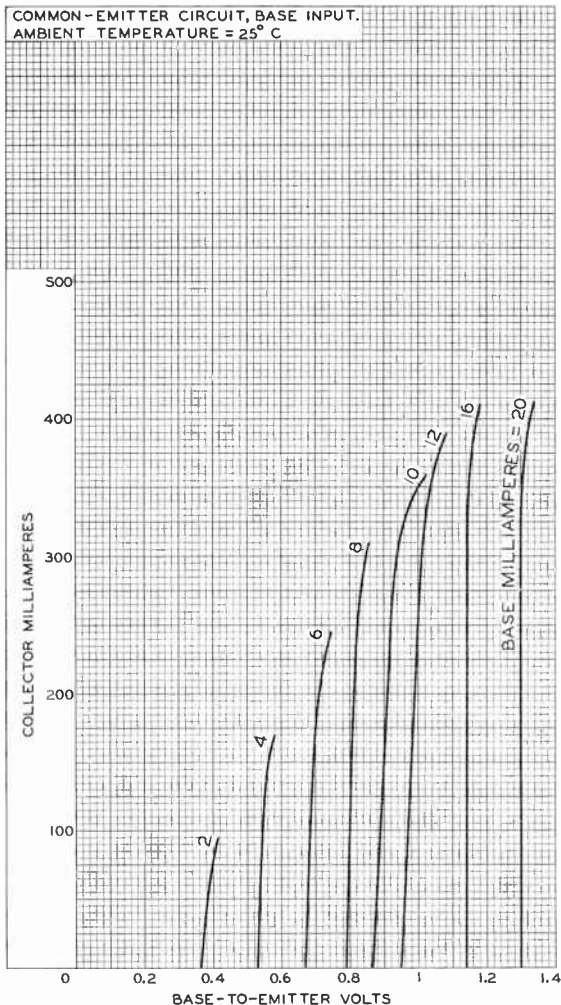
COMMON-EMITTER CIRCUIT, BASE INPUT.  
 AMBIENT TEMPERATURE = 25° C



92CM-10291



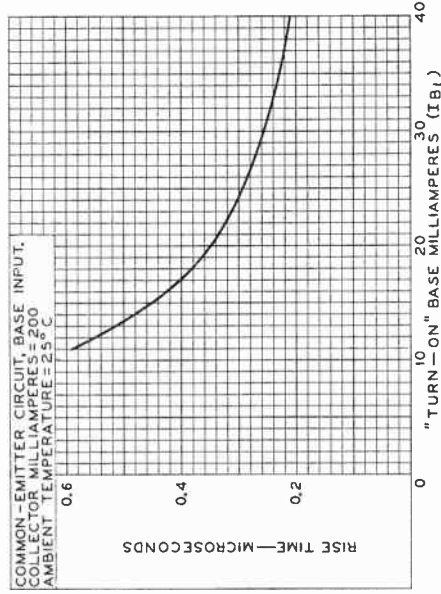
## TYPICAL TRANSFER CHARACTERISTICS



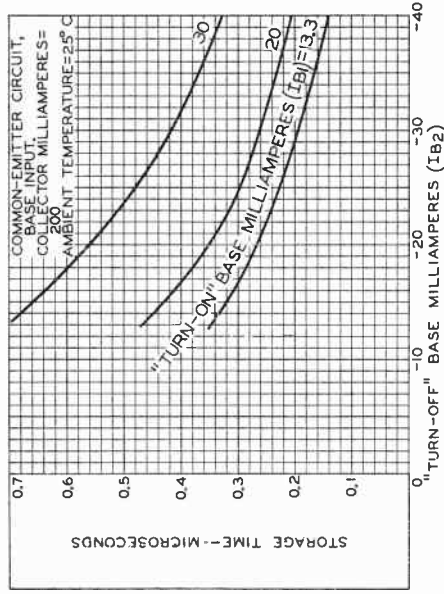
92CM-10292



## TYPICAL OPERATION CHARACTERISTICS



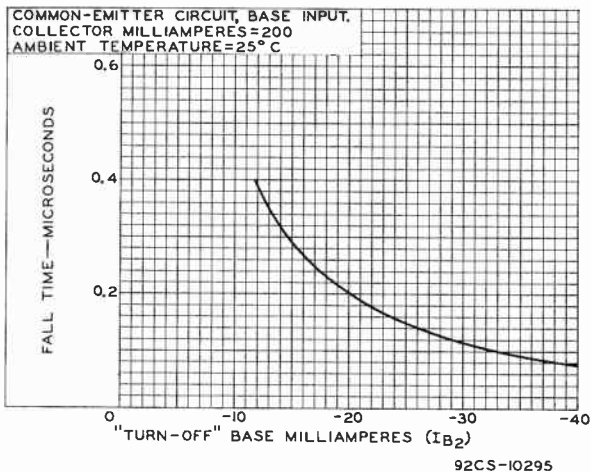
92CS-10591



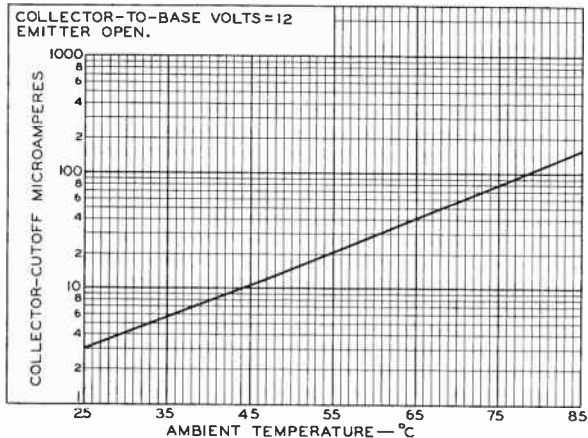
92CS-10294



## TYPICAL OPERATION CHARACTERISTIC



## TYPICAL COLLECTOR-CUTOFF-CURRENT CHARACTERISTIC



## Bidirectional Transistor

### GERMANIUM N-P-N ALLOY TYPE

For Medium-Speed Switching Service in Industrial and Military Data-Processing Systems

The 2N1170 is the same as the 2N1169 except for the following items:

### SWITCHING SERVICE

Such as in bidirectional switching, core-driver, and ac-signal-relay circuits

Maximum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE. . . . .	40 max.	volts
EMITTER-TO-BASE VOLTAGE. . . . .	40 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
Base-to-emitter volts = -1 . . . . .	39 max.	volts
Base open. . . . .	20 max.	volts

### CHARACTERISTICS RANGE VALUES FOR EQUIPMENT DESIGN

Min. Typical Max.

DC Collector Breakdown				
Voltage for dc collector				
$\mu\text{a} = -50$ , emitter open . . . . .	$BV_{CB0}$	40	50	- volts
DC Punch-Through Voltage				
for dc emitter volts				
= 1 . . . . .	$V_p$	39	50	- volts
DC Collector-Cutoff Current				
for dc collector				
volts = 12, emitter				
open . . . . .	$I_{CB0}$	-	3	8 $\mu\text{a}$





## Mesa Transistor

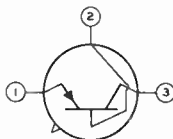
GERMANIUM P-N-P DIFFUSED-JUNCTION TYPE  
 For High-Speed Switching Service in Commercial and Military Data-Processing Systems

### GENERAL DATA

#### Mechanical:

Operating Position. . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter. . . . .	0.370"
Dimensional Outline . . . . .	JLDFC No. TO-5
Case. . . . .	Welded, Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length. . . . .	1.5"
Orientation and diameter. . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter  
 Lead 2 - Base



Lead 3 - Collector

### SWITCHING SERVICE

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	-13 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE. . . . .	-12 max.	volts
EMITTER-TO-BASE VOLTAGE <sup>a</sup> . . . . .	-1 max.	volt
COLLECTOR CURRENT . . . . .	-100 max.	ma
EMITTER CURRENT . . . . .	100 max.	ma

#### TRANSISTOR DISSIPATION:<sup>b</sup>

At ambient temperature of 25° C . . . . .	150 max.	mw
At ambient temperature of 55° C . . . . .	75 max.	mw
At ambient temperature of 71° C . . . . .	35 max.	mw

#### AMBIENT-TEMPERATURE RANGE:

Operating and storage . . . . .	-65 to +85	°C
---------------------------------	------------	----

#### LEAD TEMPERATURE:

For immersion in molten solder		
for 10 seconds maximum. . . . .	255 max.	°C

#### Typical Operation:

*In an inverter circuit at ambient temperature of 25° C*

Collector-to-Emitter Voltage. . . . .	-5	volts
Base Resistor . . . . .	5000	ohms
Collector Resistor. . . . .	500	ohms
"Turn-On" Base Voltage. . . . .	-5	volts
"Turn-Off" Base Voltage . . . . .	5	volts

← Indicates a change.



# 2N1300

"On" Collector Current. . . . .	-10	ma
"Turn-On" Base Current. . . . .	-0.66	ma
"Turn-Off" Base Current . . . . .	0.66	ma
Switching Time:		
Delay time ( $t_d$ ) . . . . .	0.14	$\mu$ sec
Rise time ( $t_r$ ) . . . . .	0.16	$\mu$ sec
Storage time ( $t_s$ ) . . . . .	0.14	$\mu$ sec
Fall time ( $t_f$ ) . . . . .	0.11	$\mu$ sec

<sup>a</sup> This rating may be exceeded and the emitter-to-base junction operated in the breakdown condition provided the emitter dissipation is limited to 30 milliwatts at 25°C. For ambient temperatures above 25°C, the dissipation should be reduced by 0.5 milliwatt/°C.

<sup>b</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## CHARACTERISTICS RANGE VALUES FOR EQUIPMENT DESIGN

Voltage values are given with respect to base unless otherwise specified. Ambient temperature of 25°C.

Min. Typical Max.

DC Collector Breakdown				
Voltage for dc collector ma. = -0.02, emitter open. . . . .	$BV_{CBO}$	-13	-30	- volts
DC Collector-to-Emitter Breakdown Voltage . . . . .	$BV_{CERL}$	-12	-25	- volts
DC Emitter Breakdown				
Voltage for dc emitter ma. = -0.1, collector open. . . . .	$BV_{EBO}$	-1	-3	- volts
DC Punch-Through Voltage. $V_p$		-12	-30	- volts
DC Base-to-Emitter				
Voltage for dc collector ma. = -40, dc base ma. = -1. . . . .	$V_{BE}$	-	-0.3	-0.4 volt
DC Collector-Cutoff				
Current for collector volts = -6, emitter open. . . . .	$I_{CBO}$	-	-1	-3 $\mu$ a
→ Collector Capacitance for dc collector volts = -6, emitter open. . . . .	$C_C$	-	8	12 $\mu$ f
DC Current Transfer Ratio for dc collector-to-emitter volts = -0.3, dc collector ma. = -10. . . . .	$h_{FE}$	30	50	-
Gain-Bandwidth Product <sup>c</sup> for collector-to-emitter volts = -3, collector ma. = -10 . . . . .	GBW	25	40	- Mc

→ indicates a change.



## Thermal Resistance:

Junction-to-free air. . . $R_T$	-	-	400	$^{\circ}\text{C}/\text{watt}$
---------------------------------	---	---	-----	--------------------------------

Total Stored Charge for				
-------------------------	--	--	--	--

dc collector ma. = -10,				
-------------------------	--	--	--	--

dc base ma. = -1. . . . $Q_S$	-	250	400	$\mu\text{coulombs}$
-------------------------------	---	-----	-----	----------------------

Thermal Time Constant . . $\tau_1$	-	10	-	msec
------------------------------------	---	----	---	------

<sup>c</sup> Frequency at which the current transfer ratio is equal to 1.

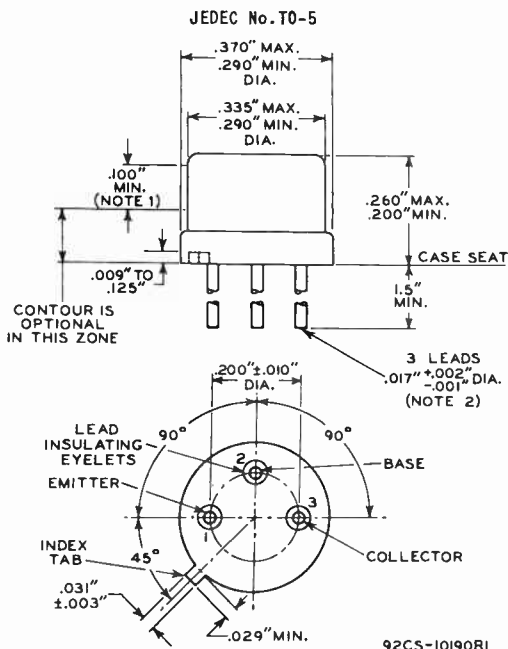
## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.



# 2N1300

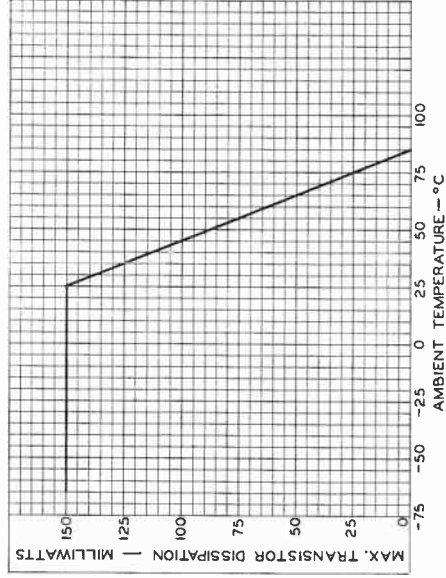


NOTE 1: THE DIAMETER IN THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE TOTAL VARIATION IN ACTUAL DIAMETER FROM THE TRUE DIAMETER, DUE TO TAPER AND OUT OF ROUND WITHIN THIS ZONE, WILL NOT EXCEED  $0.010''$ .

NOTE 2: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN  $0.05''$  AND  $0.25''$  FROM THE CASE SEAT. BETWEEN  $0.25''$  AND  $1.5''$ , A MAXIMUM DIAMETER OF  $0.021''$  IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

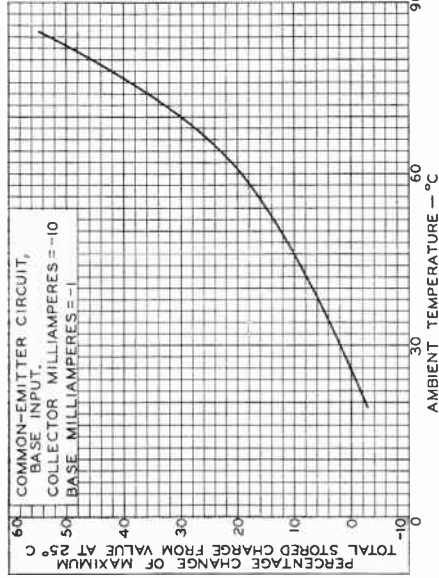


## RATING CHART



92CS-10232RI

## OPERATION CHARACTERISTIC

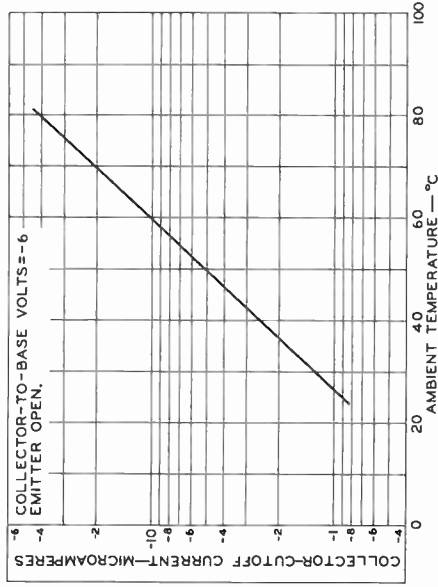


92CS-10226RI



# 2N1300

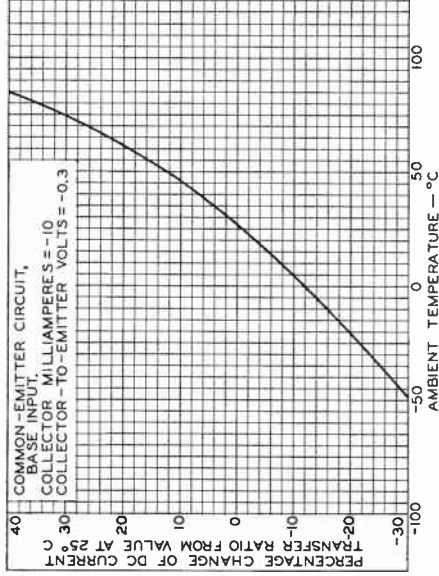
## TYPICAL COLLECTOR-CUTOFF-CURRENT CHARACTERISTIC



92CS-10213RI

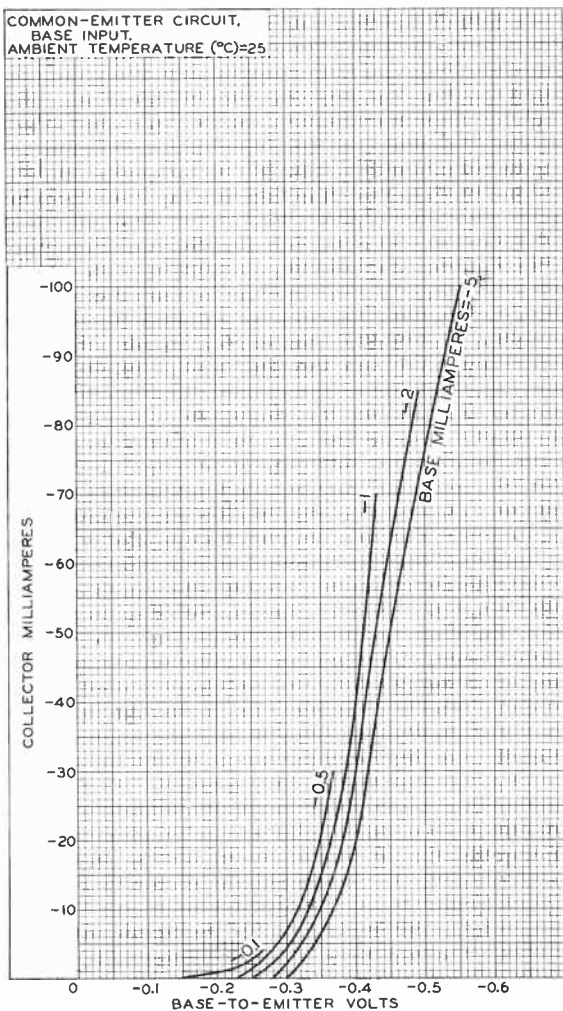
World Radio History

## TYPICAL CHARACTERISTIC



92CS-10199R3

## TYPICAL TRANSFER CHARACTERISTICS

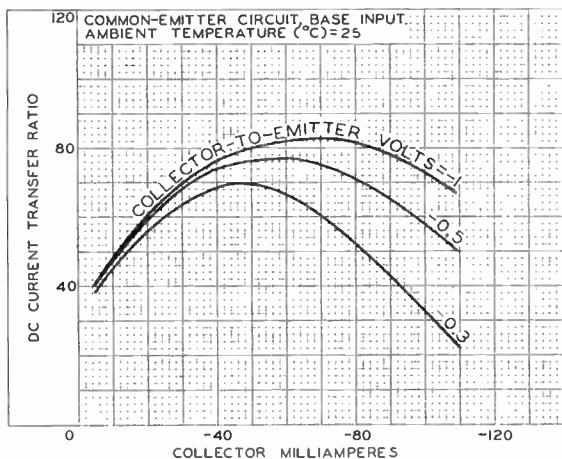


92CM-10229



# 2N1300

## TYPICAL DC CURRENT-TRANSFER-RATIO CHARACTERISTICS



92CS-10829



## Mesa Transistor

GERMANIUM P-N-P DIFFUSED-JUNCTION TYPE  
For High-Speed Switching Service in Commercial and Military Data-Processing Systems

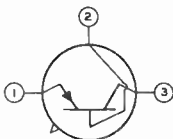
## GENERAL DATA

## Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter . . . . .	0.370"
Dimensional Outline . . . . .	JEDEC No. TO-5
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base



Lead 3 - Collector

## SWITCHING SERVICE

## Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	-13 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE . . . . .	-12 max.	volts
EMITTER-TO-BASE VOLTAGE <sup>a</sup> . . . . .	-4 max.	volts
COLLECTOR CURRENT . . . . .	-100 max.	ma
EMITTER CURRENT . . . . .	100 max.	ma
TRANSISTOR DISSIPATION: <sup>b</sup>		
At ambient temperature of 25° C . . . . .	150 max.	mw
At ambient temperature of 55° C . . . . .	75 max.	mw
At ambient temperature of 71° C . . . . .	35 max.	mw
AMBIENT-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +85	°C
LEAD TEMPERATURE:		
For immersion in molten solder for 10 seconds maximum . . . . .	255 max.	°C

## Typical Operation:

*In an inverter circuit at  
ambient temperature of 25° C*

Collector-to-Emitter Voltage . . . . .	-5	volts
Base Resistor . . . . .	2400	ohms
Collector Resistor . . . . .	120	ohms
"Turn-On" Base Voltage . . . . .	-5	volts

← Indicates a change.



# 2N1301

"Turn-Off" Base Voltage. . . . .	5	volts
"On" Collector Current . . . . .	-40	ma
"Turn-On" Base Current . . . . .	-2	ma
"Turn-Off" Base Current. . . . .	2	ma
Switching Time:		
Delay time ( $t_d$ ). . . . .	0.08	$\mu$ sec
Rise time ( $t_r$ ) . . . . .	0.07	$\mu$ sec
Storage time ( $t_s$ ). . . . .	0.12	$\mu$ sec
Fall time ( $t_f$ ) . . . . .	0.07	$\mu$ sec

<sup>a</sup> This rating may be exceeded and the emitter-to-base junction operated in the breakdown condition provided the emitter dissipation is limited to 30 milliwatts at 25° C. For ambient temperatures above 25° C, the dissipation should be reduced by 0.5 milliwatt/°C.

<sup>b</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## ELECTRICAL CHARACTERISTICS

*Voltage values are given with respect to base unless otherwise specified. Ambient temperature of 25° C.*

*Min. Typical Max.*

DC Collector Breakdown					
Voltage for dc collector ma. = -0.02, emitter open. $BV_{CBO}$					
	-13	-30	-		volts
DC Collector-to-Emitter Breakdown					
Voltage. . . . . $BV_{CERL}$					
	-12	-25	-		volts
DC Emitter Breakdown					
Voltage for dc emitter ma. = -0.1, collector open . . . $BV_{EBO}$					
	-4	-6	-		volts
DC Punch-Through					
Voltage. . . . . $V_P$					
	-12	-30	-		volts
→ DC Base-to-Emitter					
Voltage for dc collector ma. = -40, dc base ma. = -1 . . . $V_{BE}$					
	-	-0.4	-0.6		volt
DC Collector-Cutoff					
Current for collector volts = -6, emitter open . . . . $I_{CBO}$					
	-	-1	-3		$\mu$ a
→ Collector Capacitance					
for dc collector volts = -6, emitter open . . . . $C_C$					
	-	8	12		$\mu$ f
DC Current Transfer					
Ratio: $h_{FE}$					
With dc collector-to-emitter volts = -0.3, dc collector ma. = -10. . .					
	30	50	-		

→ Indicates a change.



With dc collector-to-emitter volts = -0.5, dc collector ma. = -40. . . . .	40	75	-	
Gain-Bandwidth Product <sup>c</sup> for dc collector-to-emitter volts = -3, dc collector ma. = -10 . . . GRW	35	60	-	Mc
Thermal Resistance: Junction-to-free air . . . R <sub>T</sub>	-	-	400	°C/watt
Total Stored Charge: With dc collector ma. = -10, dc base ma. = -0.4 . . . . .	-	225	325	μcoulombs
With dc collector ma. = -40, dc base ma. = -1.6 . . . . .	-	600	800	μcoulombs
Thermal Time Constant . . . τ <sub>1</sub>	-	10	-	msec

<sup>c</sup> Frequency at which the current transfer ratio is equal to 1.

### OPERATING CONSIDERATIONS

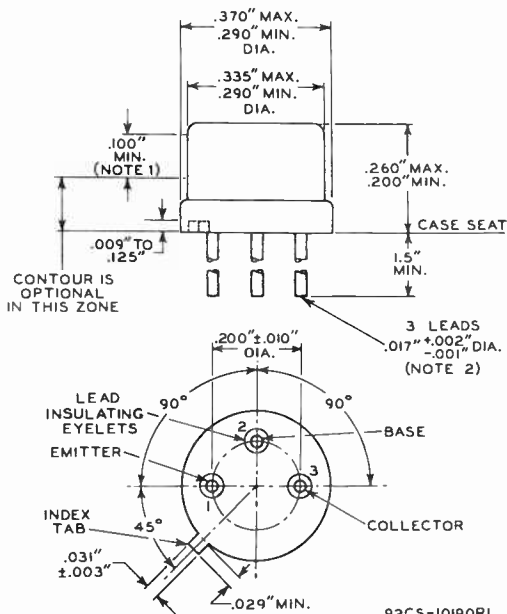
It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.



# 2N1301

JEDEC No. T0-5



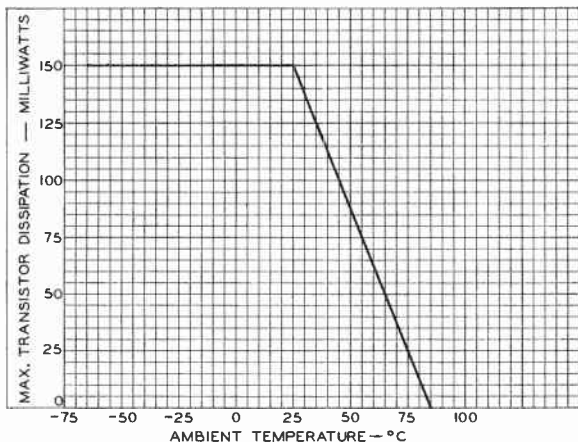
**NOTE 1:** THE DIAMETER IN THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE TOTAL VARIATION IN ACTUAL DIAMETER FROM THE TRUE DIAMETER, DUE TO TAPER AND OUT OF ROUND WITHIN THIS ZONE, WILL NOT EXCEED 0.010".

**NOTE 2:** THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE CASE SEAT. BETWEEN 0.25" AND 1.5", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.



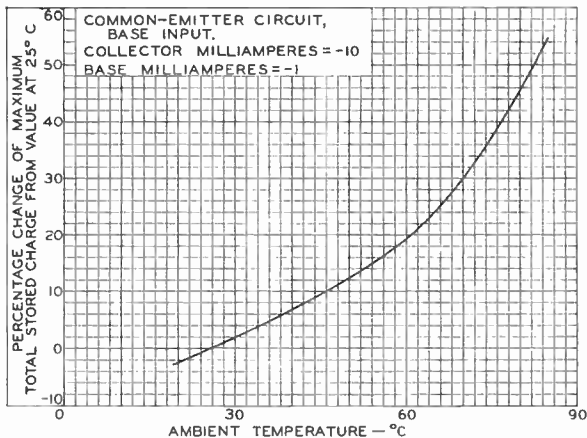


## RATING CHART



92CS-10232R1

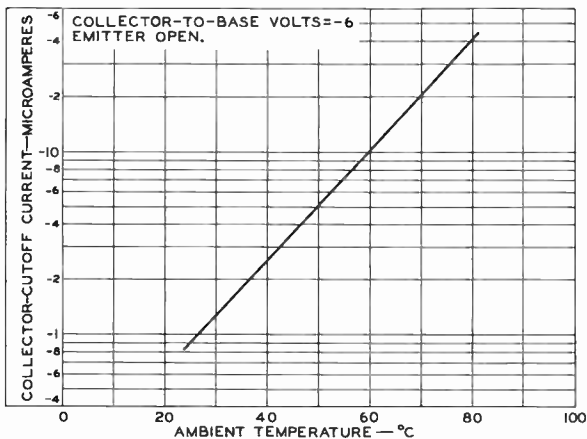
## OPERATION CHARACTERISTIC



92CS-10226R1

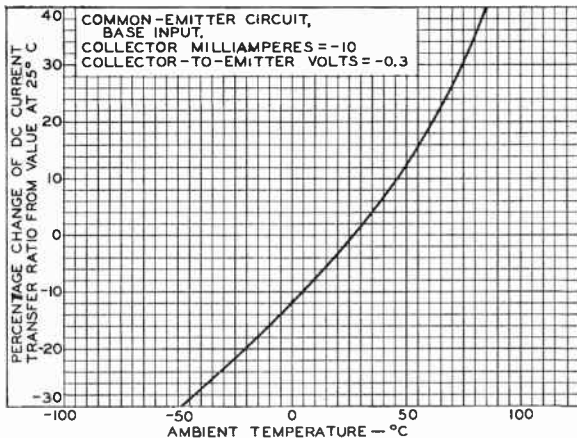


## TYPICAL COLLECTOR-CUTOFF-CURRENT CHARACTERISTIC



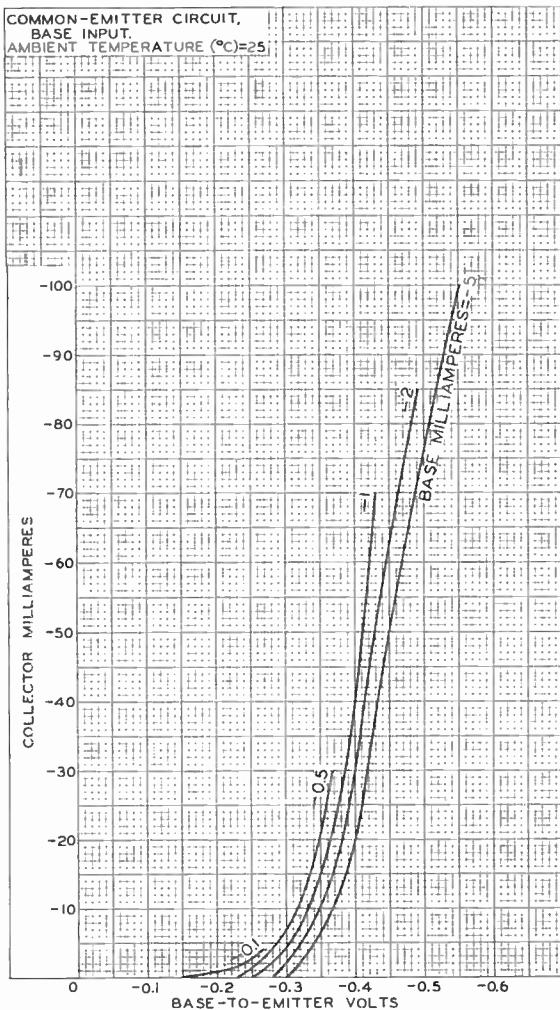
92CS-10213R1

## TYPICAL CHARACTERISTIC



92CS-10199R3

## TYPICAL TRANSFER CHARACTERISTICS



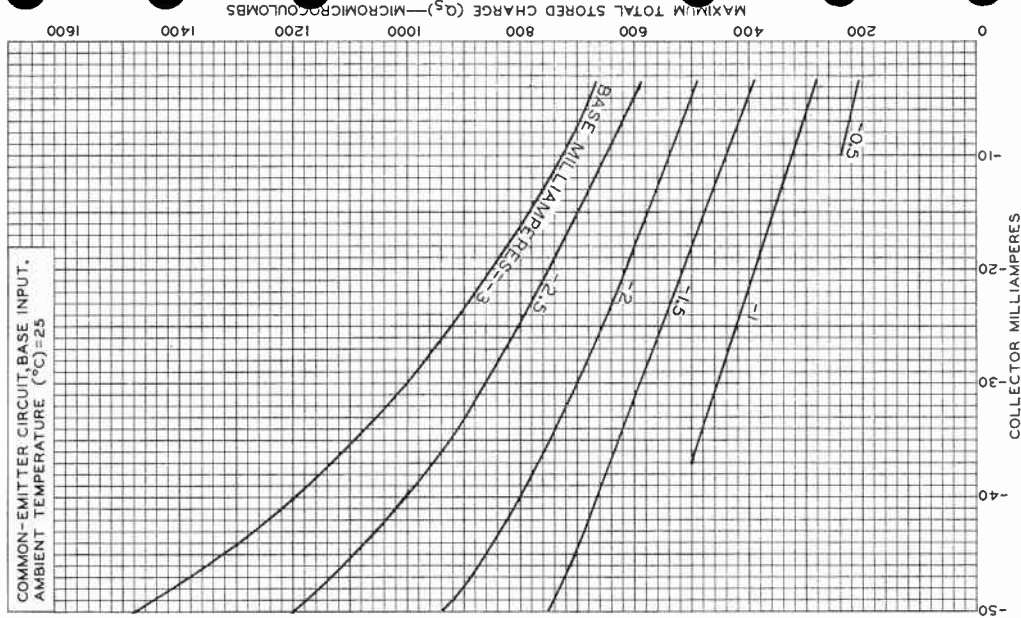
92CM-10229



# 2N1301

## MAXIMUM TOTAL- STORED-CHARGE CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT,  
AMBIENT TEMPERATURE ( $^{\circ}\text{C}$ ) = 25



MAXIMUM TOTAL STORED CHARGE ( $Q_s$ )—MICROCULOMBS

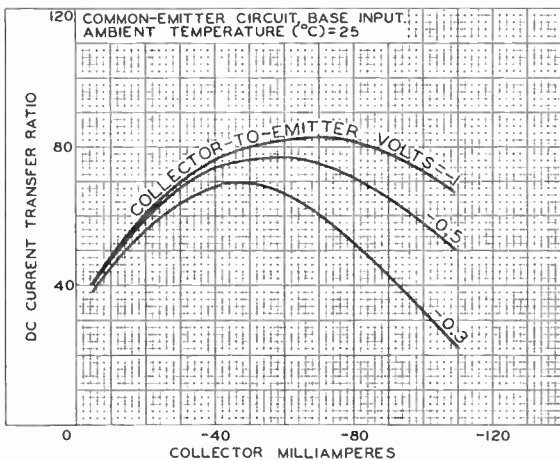
COLLECTOR MILLIAMPERES

92CM-10228



RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division  
Somerville, N. J.

## TYPICAL DC CURRENT-TRANSFER-RATIO CHARACTERISTICS



92CS-10829





# Bidirectional Transistor

## GERMANIUM P-N-P ALLOY TYPE

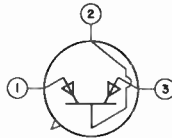
For Medium-Speed Switching Service in Industrial and Military Data-Processing Systems

### GENERAL DATA

#### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter . . . . .	0.370"
Dimensional Outline . . . . .	JEDEC No. TO-5
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter  
(Or Collector)  
Lead 2 - Base



Lead 3 - Collector  
(Or Emitter)

### SWITCHING SERVICE

*Such as in bidirectional switching, core-driver, and ac-signal-relay circuits*

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	-20 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-20 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
Base-to-emitter volts = 1 . . . . .	-20 max.	volts
COLLECTOR CURRENT . . . . .	±400 max.	ma
EMITTER CURRENT . . . . .	±400 max.	ma
TRANSISTOR DISSIPATION: <sup>a</sup>		
At ambient temperature of 25° C . . . . .	120 max.	mw
At ambient temperature of 55° C . . . . .	35 max.	mw
At ambient temperature of 71° C . . . . .	10 max.	mw
AMBIENT TEMPERATURE (During operation) . . . . .	71 max.	°C
STORAGE-TEMPERATURE RANGE . . . . .	-65 to +85	°C

#### Typical Operation:

*In accompanying typical inverter circuit at ambient temperature of 25° C*

"On" Collector Current . . . . .	200	ma
"Turn-On" Base Current ( $I_{B1}$ ) . . . . .	-20	ma
"Turn-Off" Base Current ( $I_{B2}$ ) . . . . .	20	ma



# 2N1319

## Switching Time:

Delay time ( $t_d$ ) . . . . .	0.05	$\mu$ sec
Rise time ( $t_r$ ) . . . . .	0.55	$\mu$ sec
Storage time ( $t_s$ ) . . . . .	0.7	$\mu$ sec
Fall time ( $t_f$ ) . . . . .	0.25	$\mu$ sec

<sup>a</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to the base unless otherwise specified. Ambient temperature of 25° C.

Min. Typical Max.

DC Collector Breakdown					
Voltage for dc collector $\mu a = -50$ , emitter open. . . . .	$BV_{CBO}$	-21	-35	-	volts
DC Punch-Through					
Voltage for dc emitter volts = -1. . . . .	$V_P$	-20	-35	-	volts
DC Base-to-Emitter					
Voltage for dc collector ma. = -400, dc base ma. = -26.7 . . . . .	$V_{BE}$	-	-1	-1.5	volts
DC Collector-to-Emitter					
Saturation Voltage for dc collector ma. = -400, dc base ma. = -26.7 . . . . .	$V_{CE}$	-	-0.2	-0.3	volt
DC Collector-Cutoff					
Current for dc collector volts = -12, emitter open. . . . .	$I_{CBO}$	-	-2.5	-6	$\mu a$
DC Current Transfer					
Ratio for dc collector-to-emitter volts = -0.3, dc collector ma. = -400. . . . .	$h_{FE}$	15	30	-	
Alpha-Cutoff Frequency					
for dc collector volts = -6, dc emitter ma. = 1 . . . . .	$f_{ab}$	3	6	-	Mc
Collector-to-Base Capacitance					
for dc collector volts = 6, dc emitter ma. = 0 . . . . .	$C_{ob}$	-	20	30	$\mu\mu f$
Thermal Time Constant . . . . .					
Thermal Resistance between collector junction and free air . . . . .	$R_T$	-	12	-	msec
		-	-	500	°C/watt





## OPERATING CONSIDERATIONS

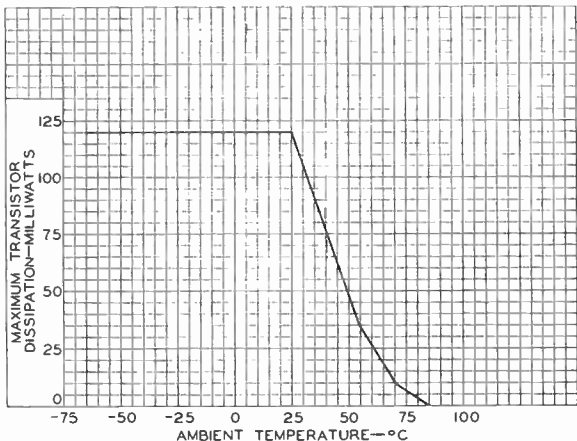
It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using this transistor, the temperature of the solder should not exceed 255° C for a maximum immersion period of 10 seconds.

This transistor is intended for use in single-side printed circuit boards and in conventional wire-in type circuits. If this transistor is used in double-side printed-circuit boards or in printed-circuit boards utilizing eyelets, it may be necessary to use an insulating washer or similar standoff device made of good dielectric material to prevent the solder from shorting the leads to each other or to the board.

## RATING CHART

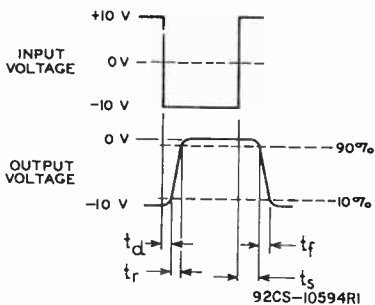
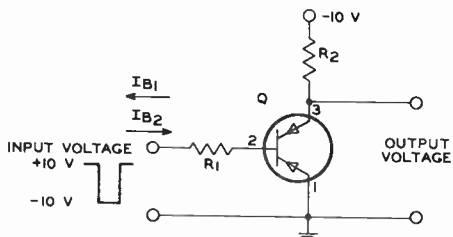


92CS-10573RI



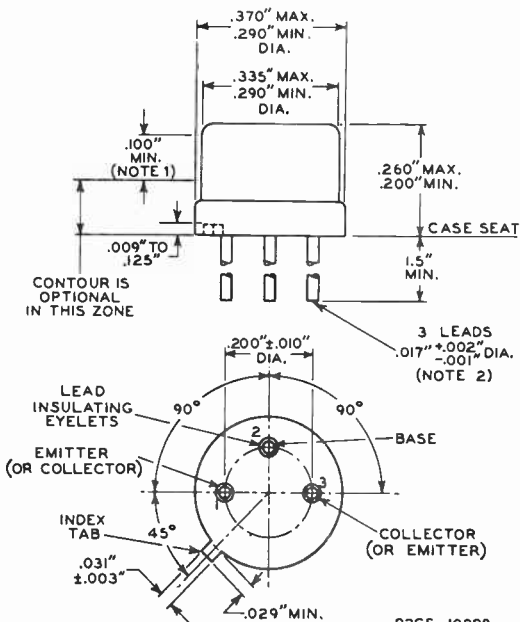
# 2N1319

## TYPICAL INVERTER CIRCUIT AND ASSOCIATED WAVEFORMS



- Q: Transistor type 2N1319
- $R_1$ : 500 ohms, 0.5 watt
- $R_2$ : 50 ohms, 0.5 watt

JEDEC No. T0-5

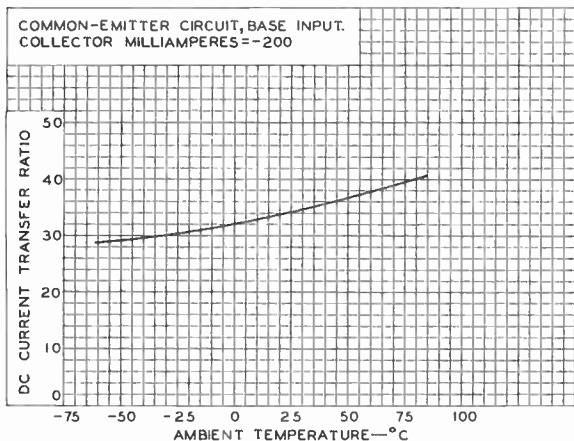


NOTE 1: THE DIAMETER IN THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE TOTAL VARIATION IN ACTUAL DIAMETER FROM THE TRUE DIAMETER, DUE TO TAPER AND OUT OF ROUND WITHIN THIS ZONE, WILL NOT EXCEED  $0.010''$ .

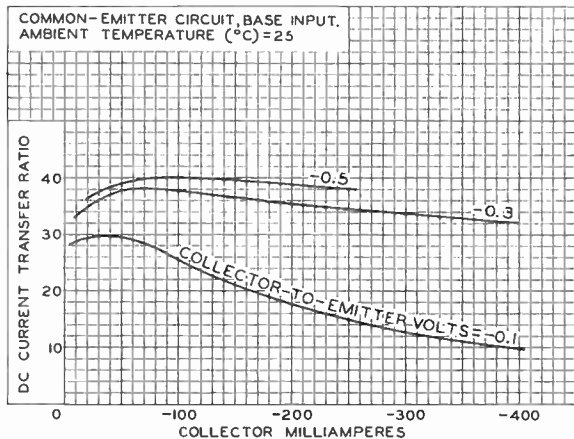
NOTE 2: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN  $0.05''$  AND  $0.25''$  FROM THE CASE SEAT. BETWEEN  $0.25''$  AND  $1.5''$ , A MAXIMUM DIAMETER OF  $0.021''$  IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.



## TYPICAL OPERATION CHARACTERISTICS

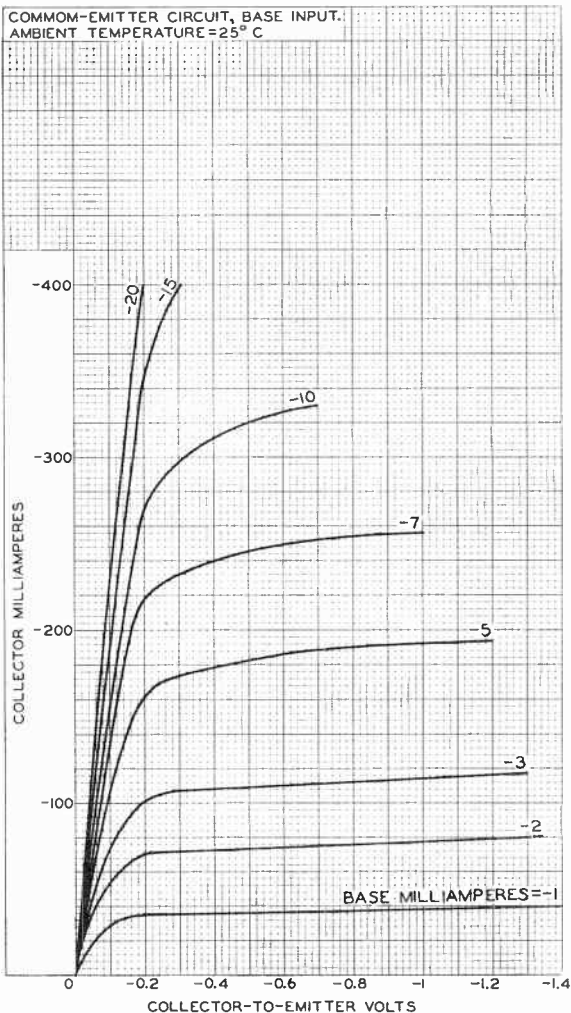


92C5-10572



92C5-10564

## TYPICAL COLLECTOR CHARACTERISTICS

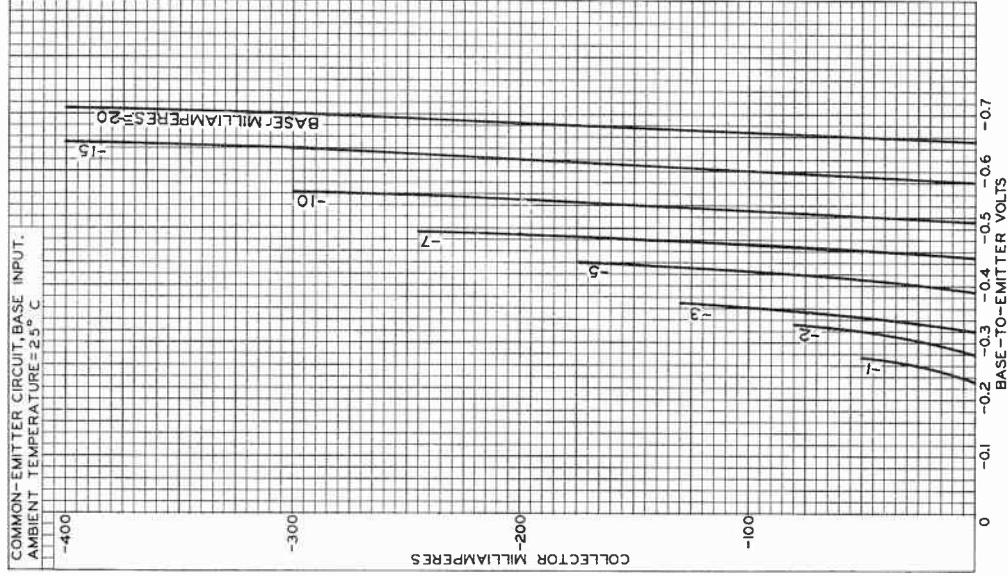


92CM-10567



# 2N1319

## TYPICAL TRANSFER CHARACTERISTICS

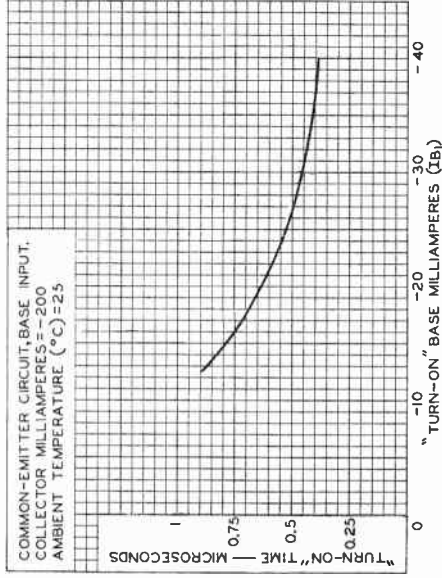


92CM--10563

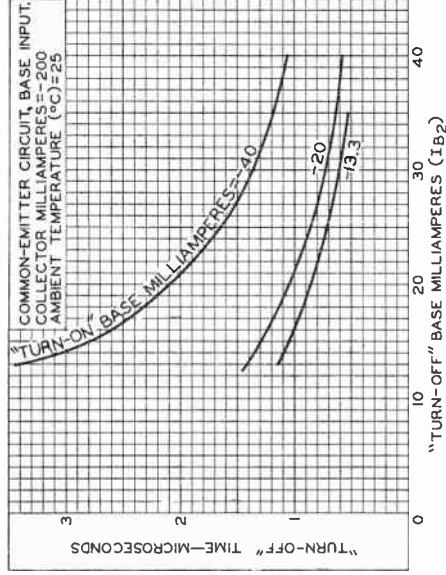


RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division  
Somerville, N. J.

## TYPICAL OPERATION CHARACTERISTICS



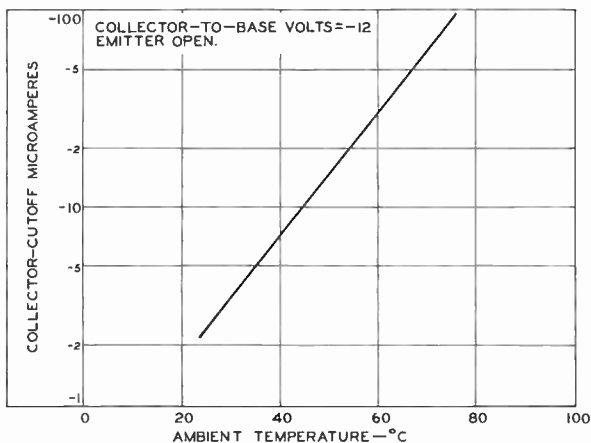
92CS-10570RI



92CS-10571RI



## TYPICAL COLLECTOR-CUTOFF-CURRENT CHARACTERISTIC



92CS-10566RI





## Power Transistor

### GERMANIUM P-N-P ALLOY TYPE

For Power Switching and Amplifier Service  
in Industrial and Military Applications

The 2N1358 is the same as the 2N174 except for the following items:

### ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and at case temperature<sup>a</sup> of 25°C unless otherwise specified

Min. Typical Max.

DC Collector-to-Emitter Break-down Voltage:					
With base connected to emitter, dc collector amperes = -0.3 . . . . .	$BV_{CES}$	-70	-	-	volts
With base open, dc collector amperes = -0.3 . . . . .	$BV_{CEO}$	-40	-	-	volts
DC Base-to-Emitter Voltage:	$V_{BE}$				
With dc collector volts = -2, dc collector amperes = -1.2 . . . . .		-	0.35	0.5	volt
With dc collector-to-emitter volts = -2, dc collector amperes = -5. . . . .		-	-0.65	-0.9	volt
DC Collector-to-Emitter Saturation Voltage for dc collector amperes = -12, dc base amperes = -2. . . . .	$V_{CE}$ ( $I_{sat}$ )	-	-0.3	-0.7	volt
DC Emitter Voltage for dc collector volts = -80, dc collector current = 0 . . . . .	$V_{EB}$	-	-0.15	-1	volt
DC Punch-Through Voltage. . . . .	$V_{PT}$	-80	-	-	volts
DC Emitter-Cutoff Current:	$I_{EBO}$				
With dc emitter volts = -30, dc collector current = 0, case temperature <sup>a</sup> = 71°C . . . . .		-	-4	-6	ma
With dc emitter volts = -60, dc collector current = 0. . . . .		-	-1	-4	ma
DC Collector-Cutoff Current:	$I_{CBO}$				
With dc collector volts = -2, dc emitter current = 0 . . . . .		-	-100	-200	$\mu$ a
With dc collector volts = -30, dc emitter current = 0, case temperature <sup>a</sup> = 71°C . . . . .		-	-4	-6	ma
With dc collector volts = -80, dc emitter current = 0 . . . . .		-	-2	-4	ma

← Indicates a change.



# 2N1358

With dc collector volts =				
-80, dc emitter current				
= 0, case temperature <sup>a</sup> =				
71° C. . . . .				
DC Current Transfer Ratio	$h_{FE}$	-	-	-15 ma
for dc collector-to-				
emitter volts = -2, dc				
collector amperes =				
-5 . . . . .	25	35	-	
-1.2 . . . . .	40	55	80	
Beta-Cutoff Frequency for				
dc collector volts = -12,				
dc collector amperes = -1. . . . .	$f_{\alpha e}$	100	-	- kc
Thermal Resistance:				
Junction-to-case . . . . .	$R_T$	-	0.35	0.5 °C/watt
Thermal Capacity for pulse				
duration of 1 to 10				
milliseconds . . . . .		-	0.075	- watt-
				sec/°C
Thermal Time Constant. . . . .	$\tau_1$	-	26.25	- msec

<sup>a</sup> Measured at any point on seating surface.



## Power Transistor

### GERMANIUM P-N-P ALLOY TYPE

For Power Switching and Amplifier Service  
in Industrial and Military Applications

The 2N1358 is the same as the 2N174 except for the following items:

### ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and case temperature of 25° C unless otherwise specified

Min. Typical Max.

DC Collector-to-Emitter Break-down Voltage:					
With base connected to emitter, dc collector amperes = -0.3 . . . . .					
	$V_{CES}$	-70	-	-	volts
With base open, dc collector amperes = -0.3 . . . . .					
	$V_{CEO}$	-40	-	-	volts
DC Base-to-Emitter Voltage* $V_{BE}$					
With dc collector volts = -2, dc collector amperes = -1.2 . . . . .					
		-	0.35	0.5	volt
With dc collector-to-emitter volts = -2, dc collector amperes = -5. . . . .					
		-	-0.65	-0.9	volt
DC Collector-to-Emitter Saturation Voltage* for dc collector amperes = -12, base amperes = -2 . . . . .					
	$V_{CE}$	-	-0.3	-0.7	volt
DC Emitter Voltage for dc collector volts = -80, dc collector amperes = 0 . . . . .					
	$V_{EB}$	-	-0.15	-1	volt
DC Punch-Through Voltage . . . . . $V_P$					
		-80	-	-	volts
DC Emitter-Cutoff Current: $I_{EBO}$					
With dc emitter volts = -30, dc collector amperes = 0, case temperature = 71° C . . . . .					
		-	-4	-6	ma
With dc emitter volts = -60, dc collector amperes = 0 . . . . .					
		-	-1	-8	ma
DC Collector-Cutoff Current: $I_{CBO}$					
With dc collector volts = -2, dc emitter amperes = 0 . . . . .					
		-	-100	-200	$\mu$ a
With dc collector volts = -30, dc emitter amperes = 0, case temperature = 71° C . . . . .					
		-	-4	-6	ma
With dc collector volts = -80, dc emitter amperes = 0 . . . . .					
		-	-2	-8	ma



# 2N1358

With dc collector volts =  
 -80, dc emitter amperes  
 = 0, case temperature =  
 71° C. . . . .

DC Current Transfer Ratio* for dc collector-to- emitter volts = -2, dc collector amperes =	$h_{FE}$	-	-	-15	ma
-5 . . . . .	25	35	-		
-1.2 . . . . .	40	55	80		
Beta-Cutoff Frequency* for dc collector volts = -12, dc collector amperes = -1. .	$f_{ae}$	100	-	-	kc
Thermal Resistance: Junction-to-case . . . . .	$R_T$	-	0.5	0.8	°C/watt
Thermal Capacity for pulse duration of 1 to 10 milliseconds . . . . .		-	0.075	-	watt- sec/°C
Thermal Time Constant. . . . .	$\tau_1$	-	37.5	-	msec

\* Measured in a common-emitter, base-input circuit.



## Drift-Field Transistor

## GERMANIUM P-N-P ALLOY TYPE

For High-Speed Switching Circuits in Industrial and Military Electronic Computers

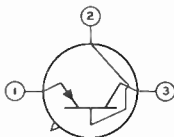
## GENERAL DATA

## Mechanical:

Operating Position. . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.390"
Maximum Diameter. . . . .	0.370"
Dimensional Outline . . . . .	JEDEC No. TO-11
Case. . . . .	Welded, Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length. . . . .	1.5"
Orientation and diameter. . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base



Lead 3 - Collector

## SWITCHING SERVICE

*Such as in memory-core-driver, pulse-amplifier, inverter, flip-flop, and logic-gate circuits*

## Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	-30 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE. . . . .	-30 max.	volts
EMITTER-TO-BASE VOLTAGE <sup>a</sup> . . . . .	-1 max.	volt
COLLECTOR CURRENT . . . . .	-500 max.	ma
EMITTER CURRENT . . . . .	500 max.	ma
TRANSISTOR DISSIPATION: <sup>b</sup>		
At ambient temperature of 25° C . . . . .	240 max.	mw
At ambient temperature of 55° C . . . . .	120 max.	mw
At ambient temperature of 71° C . . . . .	56 max.	mw
AMBIENT-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +85	°C

## Typical Operation:

*In an inverter circuit at ambient temperature of 25° C*

"On" Collector Current. . . . .	-200	ma
"Turn-On" Base Current. . . . .	-20	ma
"Turn-Off" Base Current . . . . .	20	ma
Switching Time:		
Delay time ( $t_d$ ) . . . . .	0.02	$\mu$ sec
Rise time ( $t_r$ ) . . . . .	0.08	$\mu$ sec



# 2N1384

Storage time ( $t_s$ ) . . . . .	0.25	$\mu\text{sec}$
Fall time ( $t_f$ ) . . . . .	0.1	$\mu\text{sec}$

- <sup>a</sup> This rating may be exceeded and the emitter-to-base junction operated in the breakdown condition provided the emitter dissipation is limited to 30 milliwatts at 25° C. For ambient temperatures above 25° C, reduce the dissipation by 0.5 milliwatt/°C.
- <sup>b</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## ELECTRICAL CHARACTERISTICS

*Voltage values are given with respect to the base unless otherwise specified. Ambient temperature of 25° C.*

*Min. Typical Max.*

DC Collector Breakdown				
Voltage for dc collector $\mu\text{a} = -100$ with emitter open . . . . .	$BV_{CBO}$	-30	-55	- volts
DC Collector-to-Emitter Breakdown				
Voltage . . . . .		-30	-40	- volts
DC Emitter Breakdown				
Voltage for dc emitter $\mu\text{a} = -100$ with collector open . . . . .	$BV_{EBO}$	-1	-3	- volts
DC Punch-Through				
Voltage for dc emitter volts = -1 . . . . .	$V_P$	-30	-50	- volts
→ DC Base-to-Emitter				
Voltage for dc collector ma. = -200, dc base ma. = -10 . . . . .	$V_{BE}$	-	-0.6	-0.9 volt
→ DC Collector-Cutoff				
Current for dc collector volts = -3 with emitter open . . . . .	$I_{CBO}$	-	-4	-8 $\mu\text{a}$
DC Current Transfer				
Ratio for dc collector-to-emitter volts = -0.5, dc collector ma. = -200 . . . . .	$h_{FE}$	20	50	-
Gain-Bandwidth Product <sup>c</sup>				
for collector-to-emitter volts = -3, collector ma. = -10 . . . . .	$GBW$	20	35	- Mc
Thermal Time Constant . . . . .	$\tau_T$	-	14	- msec
Thermal Resistance				
between collector junction and free air . . . . .	$R_T$	-	-	250 °C/watt
Stored Base Charge				
for dc collector ma. = -10, dc base ma. = -1 . . . . .	$Q_S$	-	600	800 $\mu\text{coulombs}$

<sup>c</sup> Frequency at which the current transfer ratio is equal to 1.

→ indicates a change.



## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

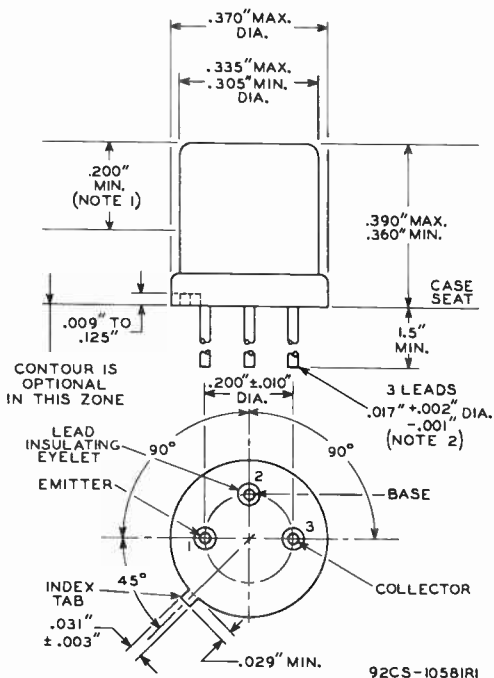
The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using this transistor, the temperature of the solder should not exceed 255° C for a maximum immersion period of 10 seconds.

This transistor is intended for use in single-side printed circuit boards and in conventional wire-in type circuits. If this transistor is used in double-side printed-circuit boards or in printed-circuit boards utilizing eyelets, it may be necessary to use an insulating washer or similar standoff device made of good dielectric material to prevent the solder from shorting the leads to each other or to the board.



# 2N1384



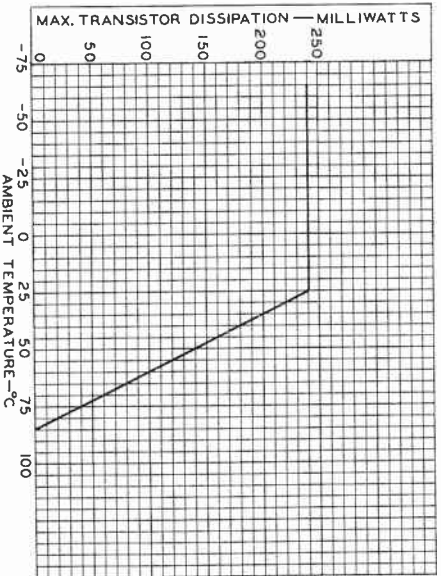
NOTE 1: THE DIAMETER IN THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE TOTAL VARIATION IN ACTUAL DIAMETER FROM THE TRUE DIAMETER, DUE TO TAPER AND OUT OF ROUND WITHIN THIS ZONE WILL NOT EXCEED 0.010".

NOTE 2: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE CASE SEAT. BETWEEN 0.25" AND 1.5", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.



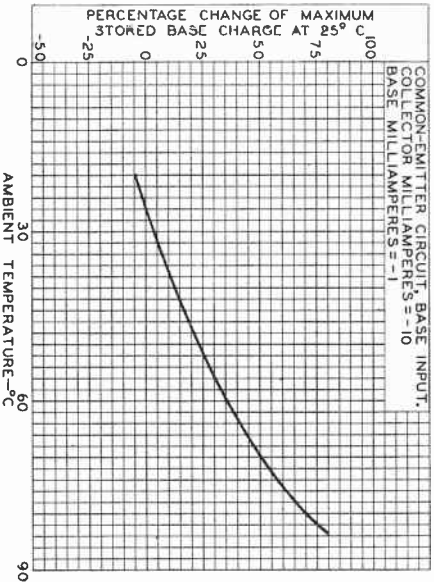
# 2N1384

## RATING CHART



92CS-10565RI

## OPERATION CHARACTERISTIC



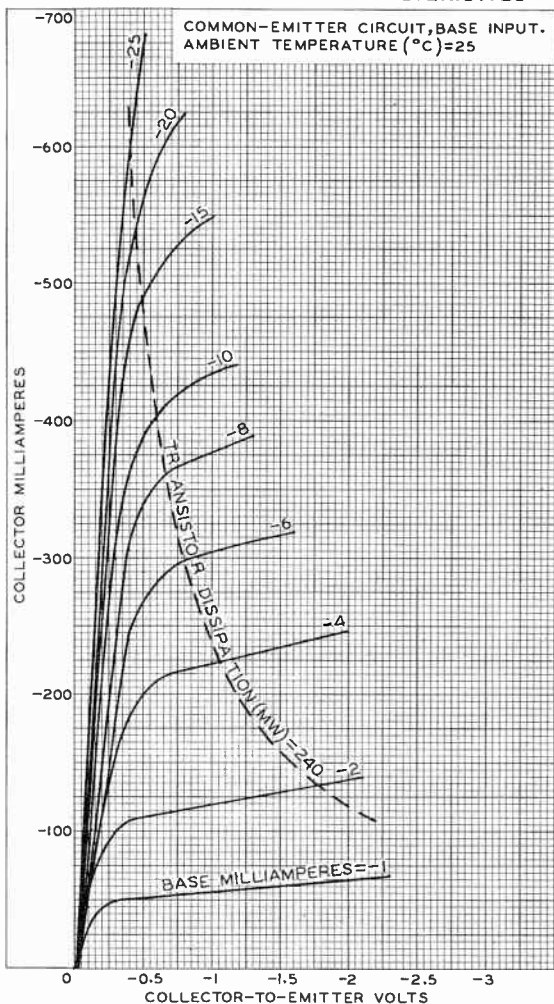
92CS-10578



RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division  
Somerville, N. J.

DATA 3  
9-60

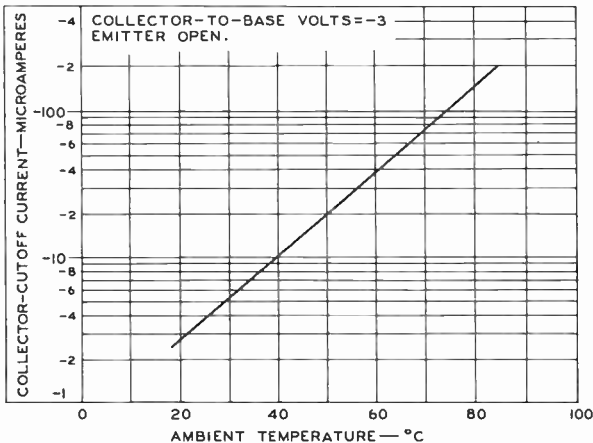
## TYPICAL COLLECTOR CHARACTERISTICS



92CM-10580

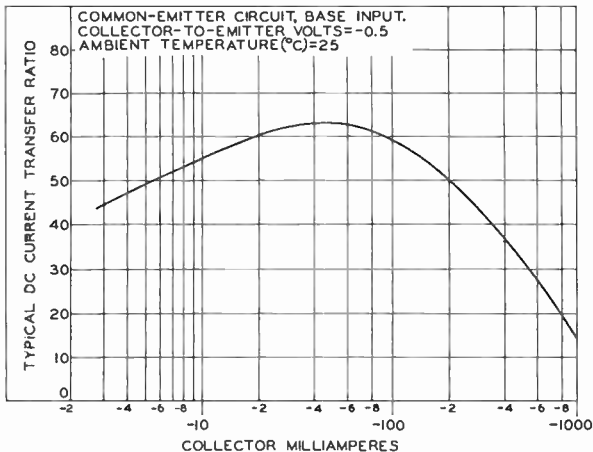


## TYPICAL COLLECTOR-CUTOFF-CURRENT CHARACTERISTIC



92CS-10568

## TYPICAL DC CURRENT-TRANSFER-RATIO CHARACTERISTIC



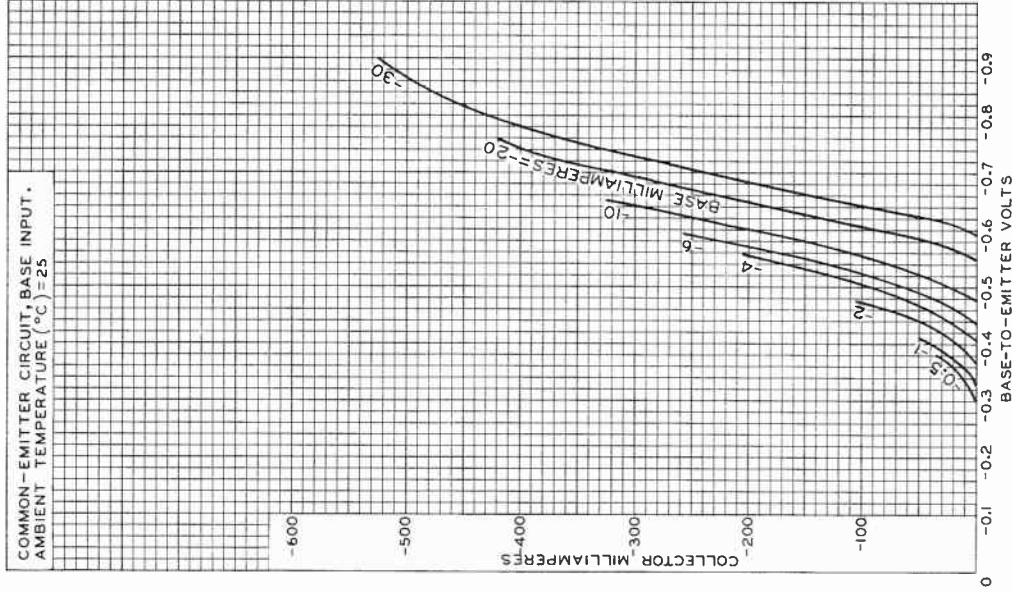
92CS-10579RI



# 2N1384

## TYPICAL TRANSFER CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT.  
AMBIENT TEMPERATURE ( $^{\circ}\text{C}$ ) = 25

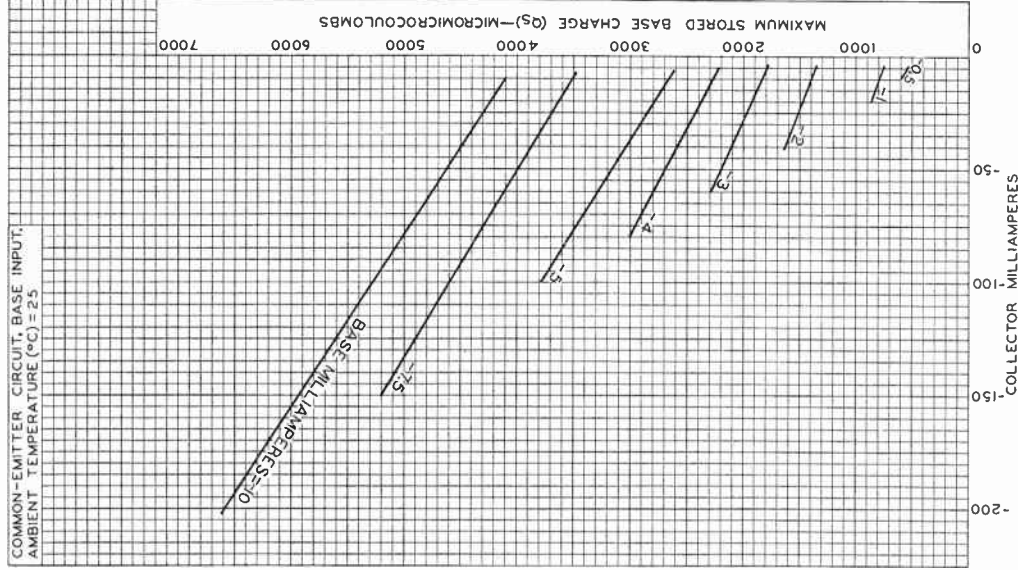


92CM-10574R2



## MAXIMUM STORED- BASE-CHARGE CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT;  
AMBIENT TEMPERATURE ( $^{\circ}\text{C}$ ) = 25



92CM-10575





## Power Transistor

### GERMANIUM P-N-P ALLOY TYPE

For Power Switching and Amplifier Service  
in Industrial and Military Applications

The 2N1412 is the same as the 2N1100 except for the following items:

### INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and audio-amplifier, relay- and solenoid-actuating circuits

Maximum and Minimum Ratings, Absolute-Maximum Values:

EMITTER-TO-BASE VOLTAGE. . . . . -60 max. volts

### ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and at case temperature<sup>a</sup> of 25° C unless otherwise specified

	Min.	Typical	Max.	
DC Base-to-Emitter Voltage for dc collector-to-emitter volts = -2, dc collector amperes = -5 . . . . .				
				$V_{BE}$ -
		-0.65	-0.8	volt
DC Emitter-Cutoff Current for dc emitter volts = -60, dc collector current = 0. . . . .				
				$I_{EBO}$ -
		-1	-4	ma

<sup>a</sup> Measured at any point on seating surface.

← Indicates a change.







## Power Transistor

### GERMANIUM P-N-P ALLOY TYPE

For Power Switching and Amplifier Service  
in Industrial and Military Applications

The 2N1412 is the same as the 2N1100 except for the following items:

#### INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and audio-amplifier, relay- and solenoid-actuating circuits

Maximum and Minimum Ratings, Absolute-Maximum Values:

EMITTER-TO-BASE VOLTAGE. . . . . -60 max. volts

#### ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and case temperature of 25° C unless otherwise specified

	Min.	Typical	Max.	
DC Base-to-Emitter Voltage* for dc collector-to-emitter volts = -2, dc collector amperes = -5 . . . . .				$V_{BE}$ -
		-0.65	-0.8	volt
DC Emitter-Cutoff Current for dc emitter volts = -60, dc collector amperes = 0. . .				$I_{EBO}$ -
		-1	-8	ma

\* Measured in a common-emitter, base-input circuit.





## Drift-Field Transistor

GERMANIUM P-N-P ALLOY TYPE

For High-Speed Switching Service in Commercial and Military Data-Processing Systems

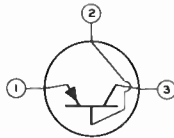
### GENERAL DATA

#### Mechanical:

Operating Position. . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter. . . . .	0.370"
Dimensional Outline . . . . .	JEDEC No. TO-9
Case. . . . .	Welded, Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length. . . . .	1.5"
Orientation and diameter. . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base



Lead 3 - Collector

### SWITCHING SERVICE

*Such as in inverter, flip-flop, and logic-gate circuits*

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE. . . . .	-30 max.	volts
EMITTER-TO-BASE VOLTAGE. . . . .	-1 max.	volt
COLLECTOR CURRENT. . . . .	-100 max.	ma
EMITTER CURRENT. . . . .	100 max.	ma
TRANSISTOR DISSIPATION: <sup>a</sup>		
At ambient temperature of 25° C. . . . .	120 max.	mw
At ambient temperature of 55° C. . . . .	60 max.	mw
At ambient temperature of 71° C. . . . .	28 max.	mw
AMBIENT-TEMPERATURE RANGE:		
Operating and storage. . . . .	-65 to +85	°C
LEAD TEMPERATURE:		
For immersion in molten solder for 10 seconds maximum . . . . .	255 max.	°C

<sup>a</sup> For ambient temperatures above 25° C, reduce the dissipation by 2 mw/°C.



# 2N1450

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base unless otherwise specified. Ambient temperature of 25° C.

		Min.	Max.	
DC Collector Breakdown Voltage for dc collector ma. = -0.1, emitter open. . . . .	$BV_{CBO}$	-30	-	volts
DC Collector-to-Emitter Breakdown Voltage for dc emitter ma. = -1, base open . . . . .	$BV_{CEO}$	-20	-	volts
Reach-Through Voltage for dc emitter ma. = -0.025. . . . .	$V_{RT}$	-20	-	volts
DC Emitter Breakdown Voltage for dc emitter ma. = -0.05, collector open. . . . .	$BV_{EBO}$	-1	-	volt
DC Base-to-Emitter Voltage for dc collector ma. = -10, dc base ma. = -0.5 . . . . .	$V_{BE}$	-	-0.6	volt
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = -10, dc base ma. = -1. . . . .	$V_{CE(sat)}$	-	-0.25	volt
DC Collector-Cutoff Current for dc collector volts = -7, emitter open. . . . .	$I_{CBO}$	-	-10	$\mu a$
DC Current Transfer Ratio for dc collector-to-emitter volts = -1, dc collector ma. = -10 .	$h_{FE}$	20	-	
"Turn-On" Time <sup>b</sup> (Rise time plus delay time). . . . .	$t_{on}$	-	100	$\mu sec$
"Turn-Off" Time <sup>b</sup> (Storage time plus fall time) . . . . .	$t_{off}$	-	85	$\mu sec$

<sup>b</sup> See accompanying Switching-Time Test Circuit and Associated Wave Forms.

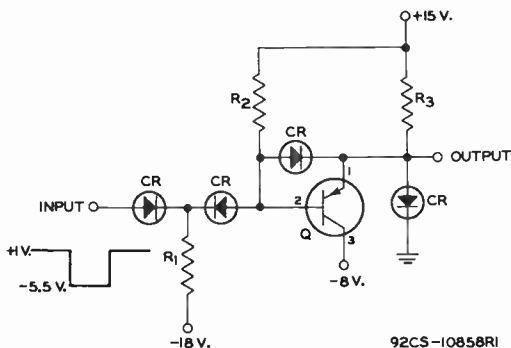
## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The flexible leads of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.

This transistor is intended for use in single-side printed-circuit boards and in conventional wire-in type circuits. If this transistor is used in double-side printed-circuit boards or in printed-circuit boards utilizing eyelets, it may be necessary to use an insulating washer or similar standoff device made of good dielectric material to prevent the solder from shorting the leads to each other or to the board.

## SWITCHING-TIME TEST CIRCUIT



CR: Semiconductor diode type 1N198-B (NOTE 2)

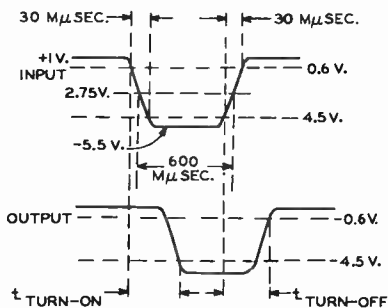
Q: Transistor type 2N1450

$R_1$ : 22,600 ohms  $\pm$  1%, 0.5 watt

$R_2$ : 82,500 ohms  $\pm$  1%, 0.5 watt

$R_3$ : 10,000 ohms  $\pm$  1%, 0.5 watt

## ASSOCIATED WAVE FORMS



92CS-10860RI

NOTE 1: TOLERANCE FOR SUPPLY VOLTAGES IS  $\pm$  1%. ALL RESISTORS ARE CARBON-COMPOSITION TYPES.

NOTE 2: THE 1N198-B SEMICONDUCTOR DIODES USED IN THIS CIRCUIT MUST SATISFY THE FOLLOWING REVERSE-RECOVERY CRITERIA AS SPECIFIED IN JAN-256 TEST CIRCUIT 14.5-2 EIA STANDARD RS-231, J14-F3, DECEMBER, 1959.

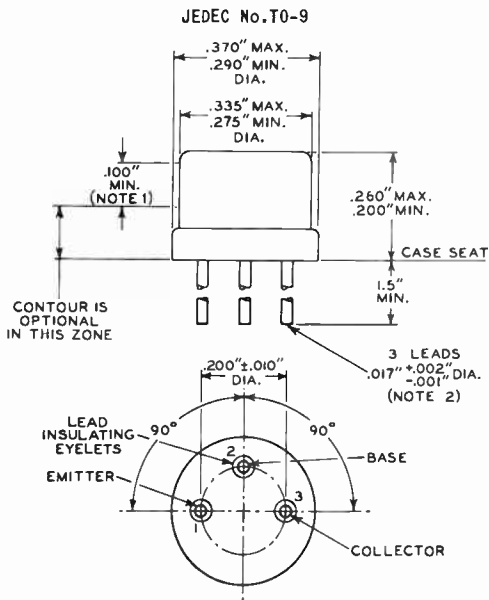


# 2N1450

THE MAXIMUM TRANSIENT VOLTAGE DEVELOPED BY THE DIODE ACROSS A 2000-OHM LOAD RESISTANCE MUST BE LESS THAN 0.3 VOLT. UNDER THESE CONDITIONS, THE PEAK REVERSE CURRENT SHALL NOT EXCEED 0.15 MILLIAMPERE AND THE REVERSE RESISTANCE SHALL NOT BE LESS THAN 40,000 OHMS.

AT 0.3 MICROSECOND AFTER THE DIODE HAS BEEN SWITCHED AS DISCUSSED IN NOTE 2, THE REVERSE RESISTANCE OF THE DIODE SHALL NOT BE LESS THAN 100,000 OHMS AND THE REVERSE CURRENT NOT MORE THAN 0.06 MA.

NOTE 3: IN THIS CIRCUIT, THE MAXIMUM LENGTH OF THE BASE LEAD OF THE TRANSISTOR SHALL BE 1 INCH, THE EMITTER LEAD 2 INCHES.



92CS-9371R7

NOTE 1: THE DIAMETER IN THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE TOTAL VARIATION IN ACTUAL DIAMETER FROM THE TRUE DIAMETER, DUE TO TAPER AND OUT OF ROUND WITHIN THIS ZONE WILL NOT EXCEED 0.010".

NOTE 2: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE CASE SEAT. BETWEEN 0.25" AND 1.5", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

## Power Transistor

SILICON N-P-N DIFFUSED-JUNCTION TYPE  
 For Power Switching and Amplifier Service  
 in Industrial and Military Applications

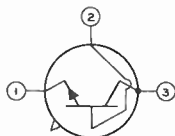
### GENERAL DATA

#### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter . . . . .	0.370"
Dimensional Outline . . . . .	JEDEC No. TO-5
Case . . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	

BOTTOM VIEW

Lead 1 - Emitter  
 Lead 2 - Base



Lead 3 - Collector,  
 Case

### INDUSTRIAL SERVICE

*Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and servo-amplifier, relay- and solenoid-actuating circuits*

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	60 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With emitter-to-base reverse biased (DC emitter-to-base volts = 1.5) . . . . .	60 max.	volts
With base open (Sustaining voltage) <sup>a</sup> . . . . .	40 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	12 max.	volts
COLLECTOR CURRENT . . . . .	1.5 max.	amp
EMITTER CURRENT . . . . .	-1.75 max.	amp
BASE CURRENT . . . . .	1 max.	amp
TRANSISTOR DISSIPATION: <sup>b</sup>		
At case temperature of 25° C . . . . .	5 max.	watts
At case temperature of 100° C . . . . .	2.86 max.	watts
CASE-TEMPERATURE RANGE: <sup>c</sup>		
Operating and storage . . . . .	-65 to +200	°C

#### Characteristics:

*At case temperature of 25° C<sup>c</sup>*

Small-Signal Current Transfer Ratio ( $h_{fe}$ ) with dc collector-to-emitter volts = 4, dc collector ma. = 5 . . . . .	50
---	----

← Indicates a change.



# 2N1479

Alpha-Cutoff Frequency ( $f_{ab}$ ) with dc collector-to-base volts = 28, dc collector ma. = 5. . . . .	1.5	Mc
Collector-to-Base Capacitance ( $C_{ob}$ ) with dc collector-to-base volts = 40 . . . . .	150	$\mu\text{mf}$
Thermal Time Constant ( $\tau_1$ ) . . . . .	10	msec

## Typical Operation:

*In accompanying typical power-switching circuit at case temperature<sup>c</sup> of 25° C*

DC Supply Voltage ( $B_2$ ) . . . . .	12	volts
DC Base-Bias Voltage ( $B_1$ ) . . . . .	-8.5	volts
"On" DC Collector Current. . . . .	200	ma
"Turn-On" Base Current ( $I_{B1}$ ) . . . . .	20	ma
"Turn-Off" Base Current ( $I_{B2}$ ) . . . . .	-8.5	ma
Generator Resistance . . . . .	50	ohms
Switching Time:		
Delay time ( $t_d$ ) . . . . .	0.2	$\mu\text{sec}$
Rise time ( $t_r$ ) . . . . .	1	$\mu\text{sec}$
Storage time ( $t_s$ ) . . . . .	0.6	$\mu\text{sec}$
Fall Time ( $t_f$ ) . . . . .	1	$\mu\text{sec}$

<sup>a</sup> The Collector-to-Emitter Sustaining Voltage ( $V_{CE0(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{AM} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

<sup>b</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

<sup>c</sup> Measured at center of seating surface.

## CHARACTERISTICS RANGE VALUES FOR EQUIPMENT DESIGN

*Voltage values are given with respect to base and case temperature<sup>c</sup> of 25° C unless otherwise specified*

Min. Max.

### Collector-to-Emitter Voltage:

With emitter reverse bias

volts = 1.5, dc collector

ma. = 0.25 . . . . .  $V_{CEX}$

60 - volts

With base open (Sustaining

voltage), dc collector

ma. = 50, dc base ma. = 0.  $V_{CE0}^a$

40 - volts

(sus)

### Base-to-Emitter Voltage for

dc collector-to-emitter

volts = 4, dc collector

ma. = 200. . . . .  $V_{BE}$

- 3 volts

### → Collector-Cutoff Current

for dc collector volts

= 30, dc emitter ma. = 0,

case temperature =

25° C . . . . .

- 10  $\mu\text{a}$

150° C . . . . .

- 500  $\mu\text{a}$

→ indicates a change.





Emitter-Cutoff Current for					
dc emitter volts = 12,					
dc collector ma. = 0 . . . . .	$I_{EBO}$	-	10	$\mu$ a	
DC Current Transfer Ratio					
for dc collector-to-emitter					
volts = 4, dc collector ma.					
= 200 . . . . .	$h_{FE}$	20	60		
DC Collector-to-Emitter					
Saturation Resistance for					
dc collector ma. = 200, dc					
base ma. = 20 . . . . .	$R_S$	-	7	ohms	
Thermal Resistance:					
Junction-to-case . . . . .	$R_T$	-	35	$^{\circ}$ C/watt	
Junction-to-free air . . . . .		-	200	$^{\circ}$ C/watt	

<sup>a</sup> The collector-to-emitter sustaining voltage ( $V_{CE0(SUS)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{QM} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

<sup>c</sup> Measured at center of sealing surface.

### OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using this transistor, the temperature of the solder should not exceed  $255^{\circ}$  C for a maximum immersion period of 10 seconds.

This transistor is intended for use in single-side printed-circuit boards and in conventional wire-in-type circuits. If this transistor is used in double-side printed-circuit boards or in printed-circuit boards utilizing eyelets, it may be necessary to use an insulating washer or similar standoff device made of good dielectric material to prevent the solder from shorting the leads to each other or to the board, and to prevent the collector from shorting to ground.

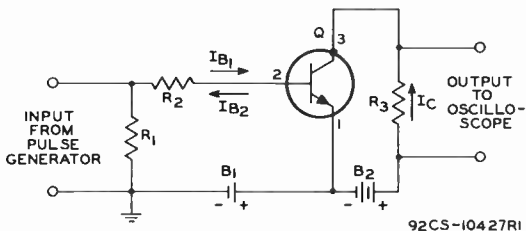
It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.

← Indicates a change.



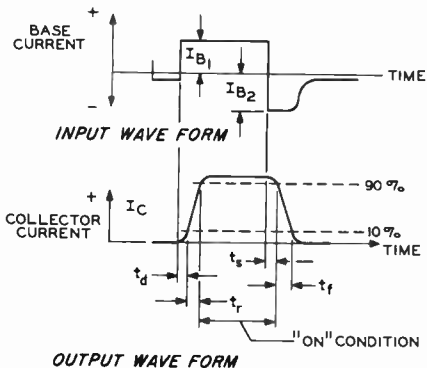
# 2N1479

## TYPICAL POWER-SWITCHING CIRCUIT



- $B_1$ : 8.5 volts
- $B_2$ : 12 volts
- Q: Transistor type 2N1479
- $R_1$ : 50 ohms, 1 watt
- $R_2$ : 700 ohms, 1 watt
- $R_3$ : 59 ohms, 2 watts

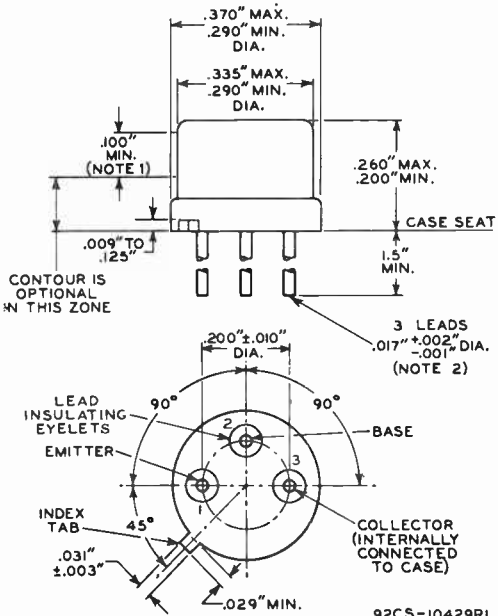
## ASSOCIATED WAVE FORMS



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JEDEC No. T0-5



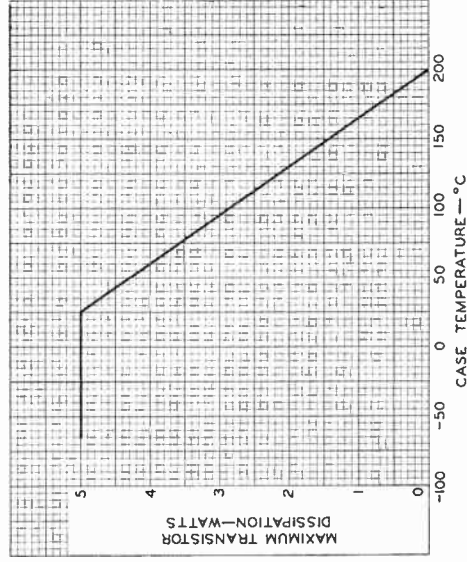
NOTE 1: THE DIAMETER IN THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE TOTAL VARIATION IN ACTUAL DIAMETER FROM THE TRUE DIAMETER, DUE TO TAPER AND OUT OF ROUND WITHIN THIS ZONE, WILL NOT EXCEED  $0.010''$ .

NOTE 2: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN  $0.05''$  AND  $0.25''$  FROM THE CASE SEAT. BETWEEN  $0.25''$  AND  $1.5''$ , A MAXIMUM DIAMETER OF  $0.021''$  IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.



# 2N1479

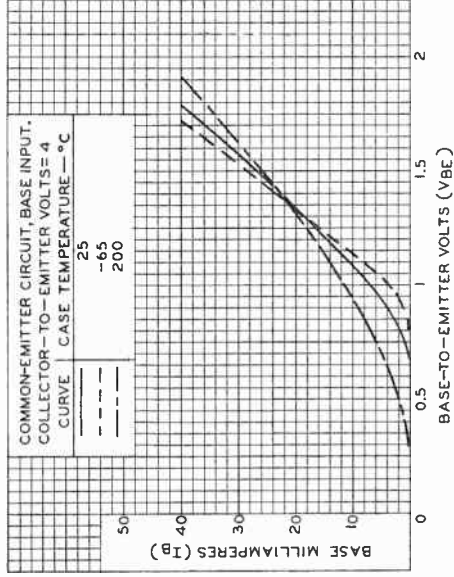
## RATING CHART



World Precision

92CS-10446R2

## TYPICAL BASE CHARACTERISTICS



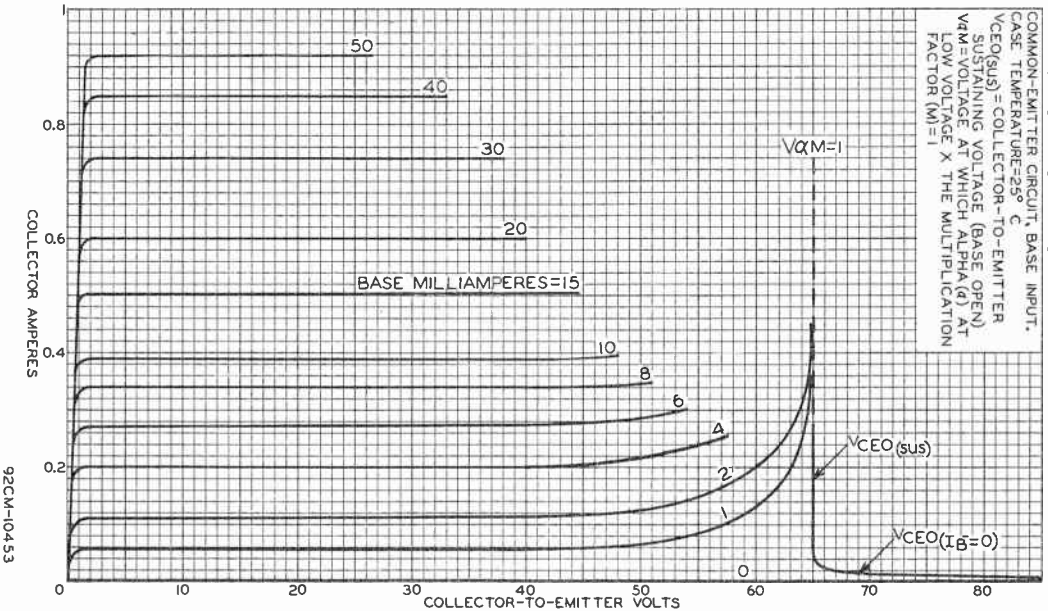
92CS-1043BR1

RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division

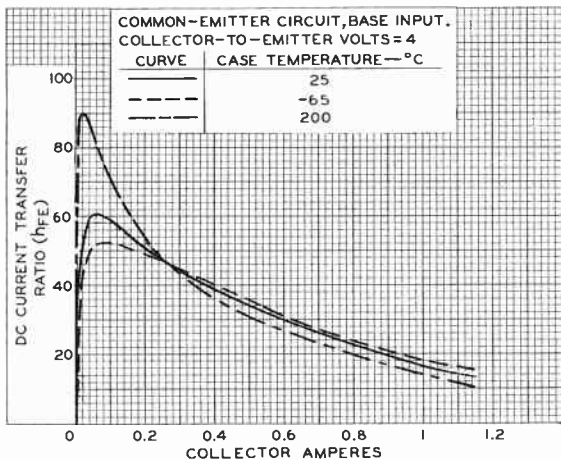
Somerville, N. J.



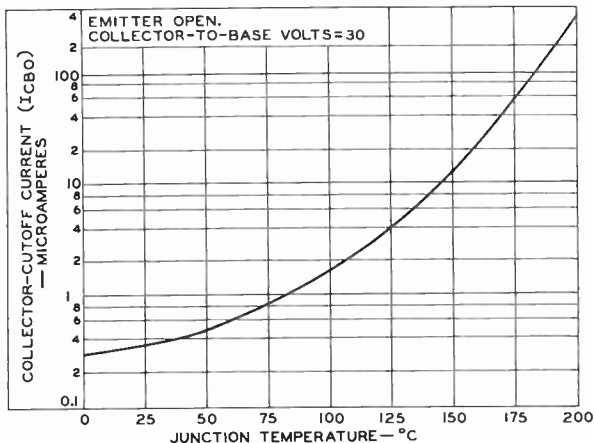
## TYPICAL COLLECTOR CHARACTERISTICS



## TYPICAL OPERATION CHARACTERISTICS



92CS-10450R1



92CS-10881

## Power Transistor

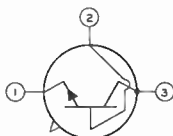
SILICON N-P-N DIFFUSED-JUNCTION TYPE  
For Power Switching and Amplifier Service  
in Industrial and Military Applications

## GENERAL DATA

## Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter . . . . .	0.370"
Dimensional Outline . . . . .	JEDEC No. TO-5
Case . . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector,  
Case

## INDUSTRIAL SERVICE

*Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and servo-amplifier, relay- and solenoid-actuating circuits*

## Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	60 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With emitter-to-base reverse biased (DC emitter-to-base volts = 1.5) . . . . .	60 max.	volts
With base open (Sustaining voltage) <sup>a</sup> . . . . .	40 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	12 max.	volts
COLLECTOR CURRENT . . . . .	1.5 max.	amp
EMITTER CURRENT . . . . .	-1.75 max.	amp
BASE CURRENT . . . . .	1 max.	amp
TRANSISTOR DISSIPATION: <sup>b</sup>		
At case temperature of 25° C . . . . .	5 max.	watts
At case temperature of 100° C . . . . .	2.86 max.	watts
CASE-TEMPERATURE RANGE: <sup>c</sup>		
Operating and storage . . . . .	-65 to +200	°C

## Characteristics:

*At case temperature of 25° C*

Small-Signal Current Transfer Ratio ( $h_{fe}$ )

with dc collector-to-emitter volts

= 4, dc collector ma. = 5 . . . . . 50

← Indicates a change.



# 2N1481

Alpha-Cutoff Frequency ( $f_{\alpha b}$ ) with dc collector-to-base volts = 28, dc collector ma. = 5. . . . .	1.5	Mc
Collector-to-Base Capacitance ( $C_{ob}$ ) with dc collector-to-base volts = 40. . . . .	150	$\mu\mu\text{f}$
Thermal Time Constant ( $\tau_1$ ). . . . .	10	msec

## Typical Operation:

*In accompanying typical power-switching circuit at case temperature of 25° C*

DC Supply Voltage ( $B_2$ ). . . . .	12	volts
DC Base-Bias Voltage ( $B_1$ ). . . . .	-8.5	volts
"On" DC Collector Current . . . . .	200	ma
"Turn-On" Base Current ( $I_{B1}$ ). . . . .	20	ma
"Turn-Off" Base Current ( $I_{B2}$ ). . . . .	-8.5	ma
Generator Resistance. . . . .	50	ohms
Switching Time:		
Delay time ( $t_d$ ) . . . . .	0.2	$\mu\text{sec}$
Rise time ( $t_r$ ). . . . .	1	$\mu\text{sec}$
Storage time ( $t_s$ ) . . . . .	0.6	$\mu\text{sec}$
Fall time ( $t_f$ ). . . . .	1	$\mu\text{sec}$

<sup>a</sup> The collector-to-Emitter Sustaining voltage ( $V_{CE0(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{\alpha M} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

<sup>b</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

<sup>c</sup> Measured at center of sealing surface.

## CHARACTERISTICS RANGE VALUES FOR EQUIPMENT DESIGN

*Voltage values are given with respect to base and case temperature of 25° C unless otherwise specified*

Min. Max.

Collector-to-Emitter Voltage:			
With emitter reverse bias volts = 1.5, dc collector ma. = 0.25. . . . .	$V_{CEX}$	60	- volts
With base open (Sustaining voltage), dc collector ma. = 50, dc base ma. = 0 .	$V_{CE0}^a$ (sus)	40	- volts
Base-to-Emitter Voltage for dc collector-to-emitter volts = 4, dc collector ma. = 200 .	$V_{BE}$	-	3 volts
Collector-Cutoff Current for dc collector volts = 30, dc emitter ma. = 0, case temperature =	$I_{CBO}$	-	10 $\mu\text{a}$
25° C . . . . .	-	10	$\mu\text{a}$
150° C. . . . .	-	500	$\mu\text{a}$
Emitter-Cutoff Current for dc emitter volts = 12, dc collector ma. = 0 . . . . .	$I_{EBO}$	-	10 $\mu\text{a}$
			→ Indicates a change.





DC Current Transfer Ratio for dc collector-to-emitter volts = 4, dc collector ma. = 200 . . . . .	$h_{FE}$	35	100	
DC Collector-to-Emitter Saturation Resistance for dc collector ma. = 200, dc base ma. = 10 . . . . .	$R_C$	-	7	ohms
Thermal Resistance:	$R_T$			
Junction-to-case. . . . .		-	35	$^{\circ}\text{C}/\text{watt}$
Junction-to-free air. . . . .		-	200	$^{\circ}\text{C}/\text{watt}$

<sup>a</sup> The Collector-to-Emitter Sustaining Voltage ( $V_{CE0(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $\alpha_M = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

**OPERATING CONSIDERATIONS,  
TYPICAL POWER-SWITCHING CIRCUIT,  
DIMENSIONAL OUTLINE,  
RATING CHART,  
and CURVES**

shown under Type 2N1479 also apply to the 2N1481

← indicates a change.





## Power Transistor

## SILICON N-P-N DIFFUSED-JUNCTION TYPE

For Power Switching and Amplifier Service  
in Industrial and Military Applications

## GENERAL DATA

## Mechanical:

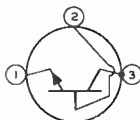
Operating Position . . . . .	Any
Maximum Overall Length . . . . .	0.770"
Maximum Seated Length . . . . .	0.330"
Maximum Diameter . . . . .	0.650"
Dimensional Outline . . . . .	JEDEC No. TO-8
Case . . . . .	Metal
Seals . . . . .	Hermetic

## Terminal Diagram:

## BOTTOM VIEW

Pin 1 - Emitter

Pin 2 - Base

Pin 3 - Collector,  
Case

## INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter, chopper,  
voltage- and current-regulator, dc- and servo-  
amplifier, relay- and solenoid-actuating circuits

## Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	60 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With emitter-to-base reverse biased (DC emitter-to-base volts = 1.5). . . . .	60 max.	volts
With base open (Sustaining voltage) <sup>a</sup> . . . . .	40 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	12 max.	volts
COLLECTOR CURRENT . . . . .	3 max.	amp
EMITTER CURRENT . . . . .	-3.5 max.	amp
BASE CURRENT . . . . .	1.5 max.	amp
TRANSISTOR DISSIPATION: <sup>b</sup>		
At case temperature of 25° C. . . . .	25 max.	watts
At case temperature of 100° C. . . . .	14.1 max.	watts
CASE-TEMPERATURE RANGE: <sup>c</sup>		
Operating and storage . . . . .	-65 to +200	°C

## Characteristics:

At case temperature of 25° C<sup>c</sup>

Alpha-Cutoff Frequency ( $f_{ab}$ ) with dc collector-to-base volts = 28, dc collector ma. = 5 . . . . .	1.25	Mc
--	------	----

← Indicates a change.



# 2N1483

Collector-to-Base Capacitance ( $C_{OB}$ )		
with dc collector-to-base volts = 40. . . . .	175	$\mu\text{f}$
Thermal Time Constant ( $\tau_1$ ). . . . .	10	msec

## Typical Operation:

*In accompanying typical power-switching circuit at case temperature<sup>c</sup> of 25° C*

DC Supply Voltage ( $B_2$ ). . . . .	12	volts
DC Base-Bias Voltage ( $B_1$ ) . . . . .	-8.5	volts
"On" DC Collector Current . . . . .	750	ma
"Turn-On" Base Current ( $I_{B1}$ ). . . . .	65	ma
"Turn-Off" Base Current ( $I_{B2}$ ) . . . . .	-35	ma
Generator Resistance. . . . .	50	ohms
Switching Time:		
Delay time ( $t_d$ ) . . . . .	0.2	$\mu\text{sec}$
Rise time ( $t_r$ ). . . . .	1	$\mu\text{sec}$
Storage time ( $t_s$ ) . . . . .	0.8	$\mu\text{sec}$
Fall time ( $t_f$ ). . . . .	1.1	$\mu\text{sec}$

<sup>a</sup> The collector-to-emitter sustaining voltage ( $V_{CEQ(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{\alpha M} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

<sup>b</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

<sup>c</sup> Measured at center of sealing surface.

## CHARACTERISTICS RANGE VALUES FOR EQUIPMENT DESIGN

*Voltage values are given with respect to base and case temperature<sup>c</sup> of 25° C unless otherwise specified*

Min. Max.

Collector-to-Emitter Voltage:			
With emitter reverse bias			
volts = 1.5, dc collector			
ma. = 0.25. . . . .	$V_{CEX}$	60	- volts
With base open (Sustaining			
voltage), dc collector			
ma. = 100, dc base ma. = 0.	$V_{CEO}^a$	40	- volts
Base-to-Emitter Voltage for	$(SUS)$		
dc collector-to-emitter			
volts = 4, dc collector			
ma. = 750 . . . . .	$V_{BE}$	-	3.5 volts
Collector-Cutoff Current	$I_{CBO}$		
for dc collector volts = 30,			
dc emitter ma. = 0, case			
temperature =			
25° C . . . . .		-	15 $\mu\text{a}$
150° C. . . . .		-	750 $\mu\text{a}$
Emitter-Cutoff Current for			
dc emitter volts = 12, dc			
emitter ma. = 0 . . . . .	$I_{EBO}$	-	15 $\mu\text{a}$
DC Current Transfer Ratio for			
dc collector-to-emitter volts			
= 4, dc collector ma. = 750 . . . . .	$h_{FE}$	20	60

→ Indicates a change.



DC (Collector-to-Emitter Saturation Resistance for dc collector ma. = 750, dc base ma. = 75 . . . . .	$R_S$	-	2.67	ohms
Thermal Resistance:	$R_T$			
Junction-to-case. . . . .		-	7	$^{\circ}\text{C}/\text{watt}$
Junction-to-free air. . . . .		-	100	$^{\circ}\text{C}/\text{watt}$

<sup>a</sup> The Collector-to-Emitter Sustaining Voltage ( $V_{CEQ(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $\alpha_M = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

<sup>c</sup> Measured at center of seating surface.

### OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

Electrical connection can be made to the collector, base, and emitter pins by means of clips or by soldering directly to the pins. Soldering of connections to the pins may be made close to the pin seats provided care is taken to conduct excessive heat away from the pin seal, otherwise the heat of the soldering operation will crack the glass seals of the pins and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using this transistor, the temperature of the solder should not exceed  $235^{\circ}\text{C}$  for a maximum immersion period of 10 seconds. Furthermore, the pins should not be dip soldered closer than  $1/32''$  from the transistor case.

Under no circumstances should the case be soldered to the heat sink because the heat of the soldering operation will permanently damage the transistor.

It is important that this transistor be securely fastened to a heat sink. Mounting clamp is provided for this purpose.

The chassis (heat sink) may be connected either to the positive or negative terminal of the voltage supply. In applications where the chassis is connected to the negative terminal of the voltage supply, it will be necessary to use an anodized-aluminum insulator having high thermal conductivity, or a  $0.002''$  mica insulator between the transistor case and the chassis. The insulator should extend beyond the mounting clamp (See *Suggested Mounting Arrangement*). An aluminum washer should be drilled or punched to provide the two mounting holes, and the clearance holes for the collector, emitter, and base pins. The burrs should then be removed from the washer and the washer finally anodized. To insure that the anodized insulating layer is not destroyed during mounting,

← Indicates a change.

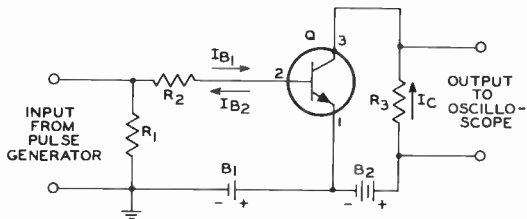


# 2N1483

it will also be necessary to remove the burrs from the holes in the chassis. Furthermore, to prevent a short circuit between the mounting bolt and the chassis, it is important that an insulating washer be used between the bolt and the chassis.

It is to be noted that the case of this transistor operates at the collector voltage. Consideration therefore, should be given to the possibility of shock hazard if the case of this transistor is to operate at a voltage appreciably above or below ground potential. In such cases, suitable precautionary measures should be taken.

## TYPICAL POWER-SWITCHING CIRCUIT



92CS-10427R1

$B_1$ : 8.5 volts

$B_2$ : 12 volts

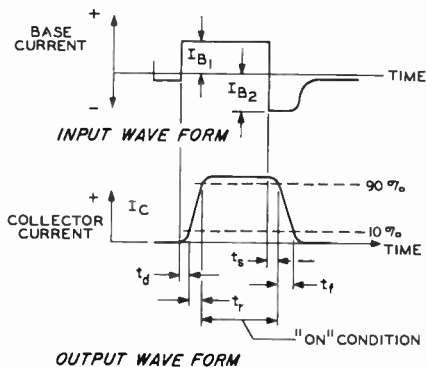
$Q$ : Transistor type 2N1483

$R_1$ : 50 ohms, 1 watt

$R_2$ : 220 ohms, 1 watt

$R_3$ : 15.9 ohms, 2 watts

## ASSOCIATED WAVE FORMS



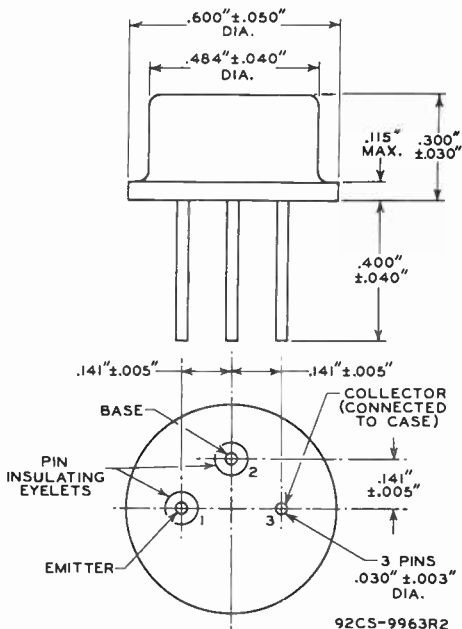
92CS-10029

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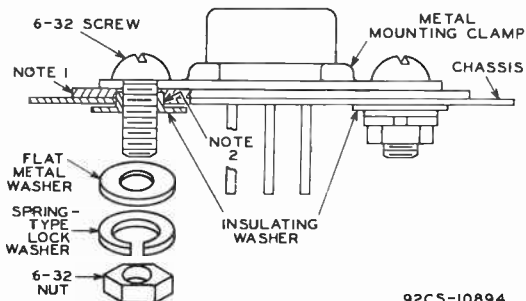
RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division  
Somerville, N. J.



JEDEC No. T0-8



### SUGGESTED MOUNTING ARRANGEMENT



NOTE 1: 0.002" MICA INSULATOR OR ANODIZED ALUMINUM INSULATOR (DRILLED, OR PUNCHED WITH BURRS REMOVED).

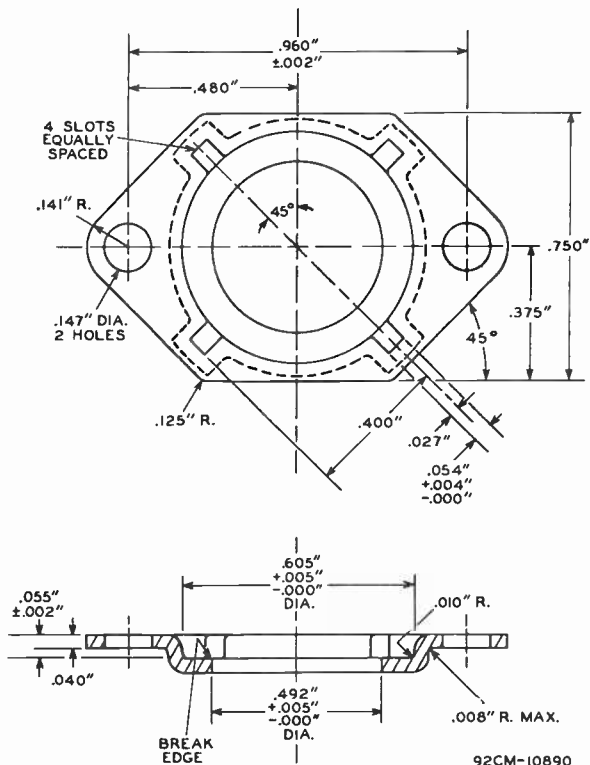
NOTE 2: REMOVE BURRS FROM CHASSIS HOLES.



# 2N1483

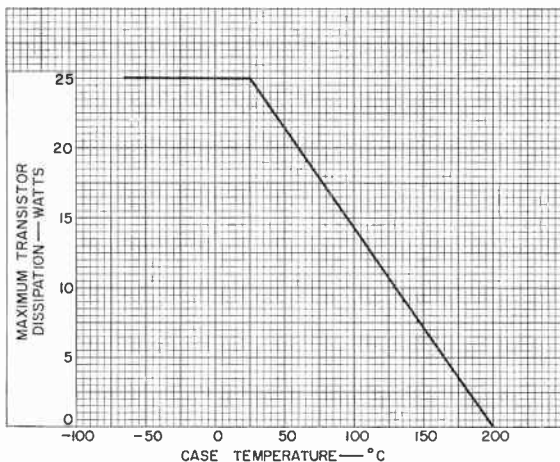
## MOUNTING CLAMP

Supplied with Each Transistor



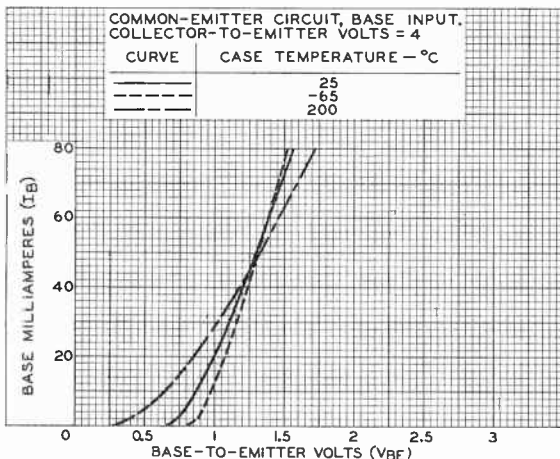


## RATING CHART



92CS-10442R2

## TYPICAL BASE CHARACTERISTICS



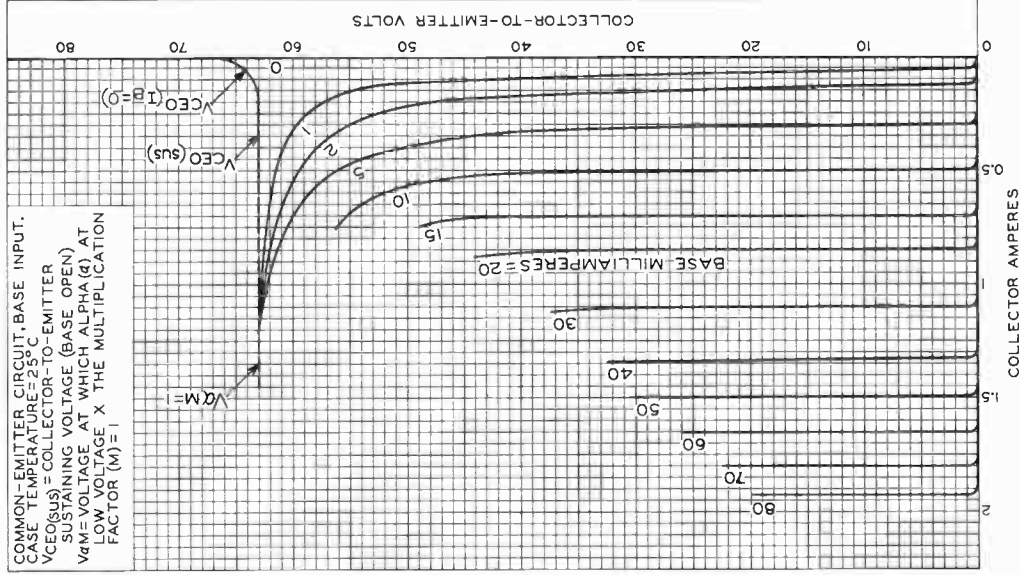
92CS-10443R3



# 2N1483

## TYPICAL COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT,  
CASE TEMPERATURE = 25°C  
 $V_{CE(sus)}$  = COLLECTOR-TO-EMITTER  
SUSTAINING VOLTAGE (BASE OPEN)  
 $V_M$  = VOLTAGE AT WHICH ALPHA ( $\alpha$ ) AT  
LOW VOLTAGE X THE MULTIPLICATION  
FACTOR ( $M$ ) = 1



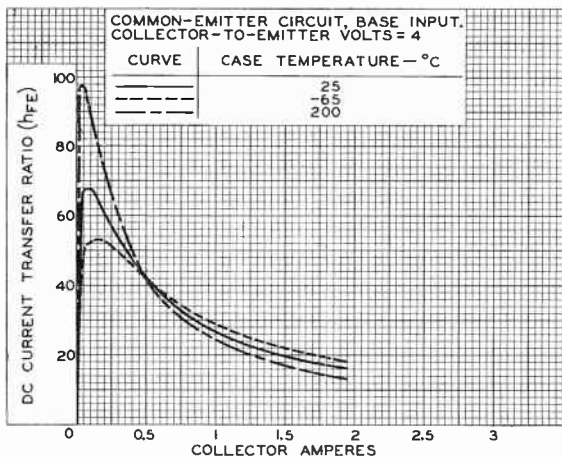
92CM-10445RI

RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division

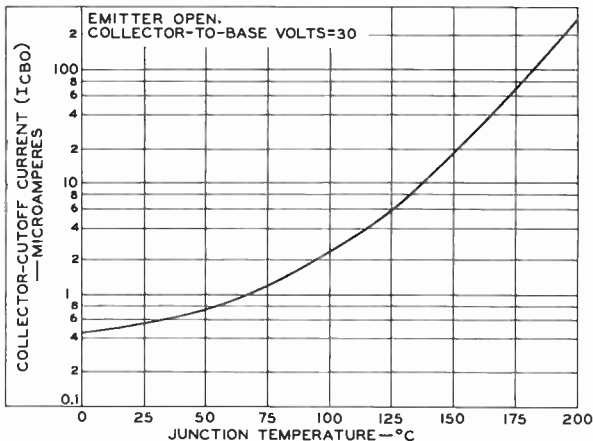
Somerville, N. J.



## TYPICAL OPERATION CHARACTERISTICS



92CS-10444R2



92CS-10882





## Power Transistor

SILICON N-P-N DIFFUSED-JUNCTION TYPE  
 For Power Switching and Amplifier Service  
 in Industrial and Military Applications

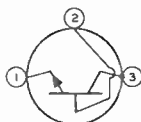
### GENERAL DATA

#### Mechanical:

Operating Position . . . . .	Any
Maximum Overall Length . . . . .	.0.770"
Maximum Seated Length . . . . .	.0.330"
Maximum Diameter . . . . .	.0.650"
Dimensional Outline . . . . .	JEDEC No. TO-8
Case . . . . .	Metal
Seals . . . . .	Hermetic

Terminal Diagram:

BOTTOM VIEW



Pin 1 - Emitter  
 Pin 2 - Base

Pin 3 - Collector,  
 Case

### INDUSTRIAL SERVICE

*Such as dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and servo-amplifier, relay- and solenoid-actuating circuits*

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	60 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With emitter-to-base reverse biased		
(DC emitter-to-base volts = 1.5). . . . .	60 max.	volts
With base open (Sustaining voltage) <sup>a</sup> . . . . .	40 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	12 max.	volts
COLLECTOR CURRENT . . . . .	3 max.	amp
EMITTER CURRENT . . . . .	-3.5 max.	amp
BASE CURRENT . . . . .	1.5 max.	amp
TRANSISTOR DISSIPATION: <sup>b</sup>		
At case temperature of 25° C. . . . .	25 max.	watts
At case temperature of 100° C. . . . .	14.1 max.	watts
CASE TEMPERATURE RANGE: <sup>c</sup>		
Operating and storage . . . . .	-65 to +200	°C

#### Characteristics:

*At case temperature of 25° C<sup>c</sup>*

Alpha-Cutoff Frequency ( $f_{ab}$ ) with dc		
collector-to-base volts = 28, dc		
collector ma. = 5 . . . . .	1.25	Mc

← Indicates a change.



# 2N1485

Collector-to-Base Capacitance ( $C_{ob}$ )			
with dc collector-to-base volts = 40. . . . .	175	$\mu\text{mf}$	
Thermal Time Constant ( $\tau_1$ ). . . . .	10	msec	

## Typical Operation:

*In accompanying typical power-switching circuit at case temperature<sup>c</sup> of 25° C*

DC Supply Voltage ( $B_2$ ). . . . .	12	volts
DC Base-Bias Voltage ( $B_1$ ) . . . . .	-8.5	volts
"On" DC Collector Current . . . . .	750	ma
"Turn-On" Base Current ( $I_{B1}$ ). . . . .	65	ma
"Turn-Off" Base Current ( $I_{B2}$ ) . . . . .	-35	ma
Generator Resistance. . . . .	50	ohms
Switching Time:		
Delay time ( $t_d$ ) . . . . .	0.2	$\mu\text{sec}$
Rise time ( $t_r$ ) . . . . .	1	$\mu\text{sec}$
Storage time ( $t_s$ ) . . . . .	0.8	$\mu\text{sec}$
Fall time ( $t_f$ ) . . . . .	1.1	$\mu\text{sec}$

<sup>a</sup> The Collector-to-Emitter Sustaining Voltage ( $V_{CE0(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{AM} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

<sup>b</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

<sup>c</sup> Measured at center of seating surface.

## CHARACTERISTICS RANGE VALUES FOR EQUIPMENT DESIGN

*Voltage values are given with respect to base and case temperature<sup>c</sup> of 25° C unless otherwise specified*

	Min.	Max.	
Collector-to-Emitter Voltage:			
With emitter reverse bias			
volts = 1.5, dc collector			
ma. = 0.25. . . . .	$V_{CEX}$	60	- volts
With base open (Sustaining			
voltage), dc collector			
ma. = 100, dc base			
ma. = 0 . . . . .	$V_{CE0}^a$ (sus)	40	- volts
Base-to-Emitter Voltage			
for dc collector-to-emitter			
volts = 4, dc collector			
ma. = 750 . . . . .	$V_{BE}$	-	2.5 volts
→ Collector-Cutoff Current	$I_{CBO}$		
for dc collector volts			
= 30, dc emitter ma. = 0,			
case temperature =			
25° C . . . . .		-	15 $\mu\text{a}$
150° C. . . . .		-	750 $\mu\text{a}$
Emitter-Cutoff Current for			
dc emitter volts = 12,			
dc emitter ma. = 0. . . . .	$I_{EBO}$	-	15 $\mu\text{a}$

→ Indicates a change.



DC Current Transfer Ratio  
for dc collector-to-emitter  
volts = 4, dc collector ma.  
= 750. . . . .

$h_{FE}$	35	100
----------	----	-----

DC Collector-to-Emitter  
Saturation Resistance for  
dc collector ma. = 750, dc  
base ma. = 40. . . . .

$R_S$	-	1	ohm
-------	---	---	-----

Thermal Resistance:

$R_T$	-	7	°C/watt ←
-------	---	---	-----------

Junction-to-case . . . . .

-	7	°C/watt
---	---	---------

Junction-to-free air . . . . .

-	100	°C/watt
---	-----	---------

<sup>a</sup> The Collector-to-Emitter Sustaining Voltage ( $V_{CE0(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{\alpha M} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

<sup>c</sup> Measured at center of seating surface.

OPERATING CONSIDERATIONS,  
TYPICAL POWER-SWITCHING CIRCUIT,  
DIMENSIONAL OUTLINE,  
RATING CHART,  
and CURVES

shown under Type 2N1483 also apply to the 2N1485

← Indicates a change.







## Power Transistor

SILICON N-P-N DIFFUSED-JUNCTION TYPE  
 For Power Switching and Amplifier Service  
 in Industrial and Military Applications

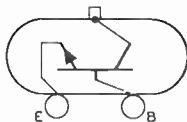
### GENERAL DATA

#### Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	0.865"
Maximum Seated Length. . . . .	0.390"
Maximum Length of Mounting Flange. . . . .	1.550"
Maximum Width of Mounting Flange. . . . .	1.015"
Case. . . . .	Metal
Mounting Flange. . . . .	Metal
Seals. . . . .	Hermetic
Socket. . . . .	Loranger Mfg. Corp. No.2149, or equivalent
Terminal Diagram (See <i>Dimensional Outline</i> ):	

E - Emitter

B - Base



MOUNTING FLANGE-  
 Collector,  
 Case

### INDUSTRIAL SERVICE

*Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and servo-amplifier, relay- and solenoid-actuating circuits*

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE. . . . .	60 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With emitter-to-base reverse biased (DC emitter-to-base volts = 1.5) . . . . .	60 max.	volts
With base open (Sustaining voltage) <sup>a</sup> . . . . .	40 max.	volts
EMITTER-TO-BASE VOLTAGE. . . . .	10 max.	volts
COLLECTOR CURRENT. . . . .	6 max.	amp
EMITTER CURRENT. . . . .	-8 max.	amp
BASE CURRENT . . . . .	3 max.	amp
TRANSISTOR DISSIPATION: <sup>b</sup>		
At mounting-flange temperature of 25° C. . . . .	75 max.	watts
At mounting-flange temperature of 100° C. . . . .	43 max.	watts
MOUNTING-FLANGE TEMPERATURE RANGE: <sup>c</sup>		
Operating and storage. . . . .	-65 to +200	°C

#### Characteristics:

*At mounting-flange temperature of 25° C*

Alpha-Cutoff Frequency ( $f_{ab}$ ) with dc collector-to-base volts = 12, dc collector ma. = 100 . . . . .	1	Mc
--	---	----

← Indicates a change.



# 2N1487

Collector-to-Base Capacitance ( $C_{ob}$ )			
with dc collector-to-base volts = 40 . . . . .	200		$\mu\mu\text{f}$
Thermal Time Constant ( $\tau_1$ ) . . . . .	12		msec

## Typical Operation:

*In accompanying typical power-switching circuit at mounting-flange temperature<sup>c</sup> of 25° C*

DC Supply Voltage ( $B_2$ ) . . . . .	12	volts
DC Base-Bias Voltage ( $B_1$ ) . . . . .	-8.5	volts
"On" DC Collector Current . . . . .	1.5	amp
"Turn-On" Base Current ( $I_{B1}$ ) . . . . .	0.3	amp
"Turn-Off" Base Current ( $I_{B2}$ ) . . . . .	-0.15	amp
Generator Resistance . . . . .	50	ohms
Switching Time:		
Delay Time ( $t_d$ ) . . . . .	0.2	$\mu\text{sec}$
Rise Time ( $t_r$ ) . . . . .	1	$\mu\text{sec}$
Storage Time ( $t_s$ ) . . . . .	1	$\mu\text{sec}$
Fall Time ( $t_f$ ) . . . . .	1.2	$\mu\text{sec}$

<sup>a</sup> The Collector-to-Emitter Sustaining voltage ( $V_{CEQ(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $\alpha_{EM} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

<sup>b</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

<sup>c</sup> Measured at center of seating surface.

## CHARACTERISTICS RANGE VALUES FOR EQUIPMENT DESIGN

*Voltage values are given with respect to base and mounting-flange temperature<sup>c</sup> of 25° C unless otherwise specified*

Min. Max.

Collector-to-Emitter Voltage:			
With emitter reverse bias			
volts = 1.5, dc collector			
ma. = 0.5 . . . . . $V_{CEX}$	60	-	volts
With base open (Sustaining			
voltage), dc collector			
ma. = 100, dc base ma. = 0. $V_{CEO}^a$	40	-	volts
( $sus$ )			
Base-to-Emitter Voltage for			
dc collector-to-emitter volts			
= 4, dc collector amperes = 1.5 $V_{BE}$	-	3.5	volts
Collector-Cutoff Current $I_{CBO}$			
for dc collector volts =			
30, dc emitter ma. = 0,			
mounting-flange temperature =			
25° C . . . . .	-	25	$\mu\text{a}$
150° C . . . . .	-	1000	$\mu\text{a}$
Emitter-Cutoff Current for dc			
emitter volts = 10, dc			
collector ma. = 0. . . . . $I_{EBO}$	-	25	$\mu\text{a}$
DC Current Transfer Ratio			
for dc collector-to-emitter			
volts = 4, dc collector			
amperes = 1.5. . . . . $h_{FE}$	15	45	

→ Indicates a change.



## DC Collector-to-Emitter

Saturation Resistance for

dc collector amperes = 1.5,

dc base ma. = 300. . . . .  $R_S$  - 2 ohms

## Thermal Resistance:

Junction-to-mounting-flange.  $R_T$  - 2.33 °C/watt ←

<sup>a</sup> The Collector-to-Emitter Sustaining Voltage ( $V_{CE(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{CEM} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

<sup>c</sup> Measured at center of sealing surface.

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

This transistor utilizes the Loranger Mfg. Corp. socket No. 2149, or equivalent. Electrical connection can also be made to the base and emitter pins by soldering directly to the pins. Soldering of connections to the pins may be made close to the pin seals provided care is taken to conduct excessive heat away from the pin seal, otherwise the heat of the soldering operation will crack the glass seals of the pins and damage the transistor.

Under no circumstances should the mounting flange be soldered to the heat sink because the heat of the soldering operation will permanently damage the transistor.

It is important that the mounting flange which serves as the collector terminal be securely fastened to a heat sink. Depending on the application, the chassis (heat sink) may be connected either to the positive or negative terminal of the voltage supply.

In applications where the chassis is connected to the negative terminal of the voltage supply, it will be necessary to use an anodized-aluminum insulator having high thermal conductivity, or a 0.002" mica insulator between the mounting flange and the chassis. An aluminum washer should be drilled or punched to provide the two mounting holes, and the clearance holes for the emitter and base pins. The burrs should then be removed from the washer and the washer finally anodized. To insure that the anodized insulating layer is not destroyed during mounting, it will also be necessary to remove the burrs from the holes in the chassis. Furthermore, to prevent a short circuit between the mounting bolt and the chassis, it is important that an insulating washer be used between the bolt and the chassis (See *Suggested Mounting Arrangement*).

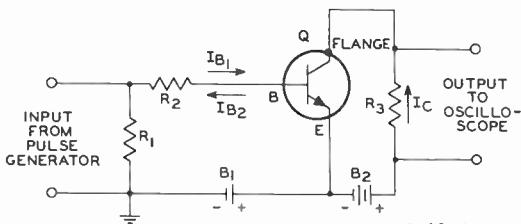
It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.

← Indicates a change.



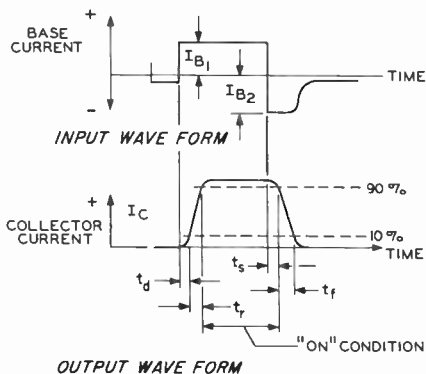
# 2N1487

## TYPICAL POWER-SWITCHING CIRCUIT



- $B_1$  = 8.5 volts
- $B_2$  = 12 volts
- Q = Transistor type 2N1487
- $R_1$  = 50 ohms, 1 watt
- $R_2$  = 30 ohms, 1 watt
- $R_3$  = 7.8 ohms, 2 watts

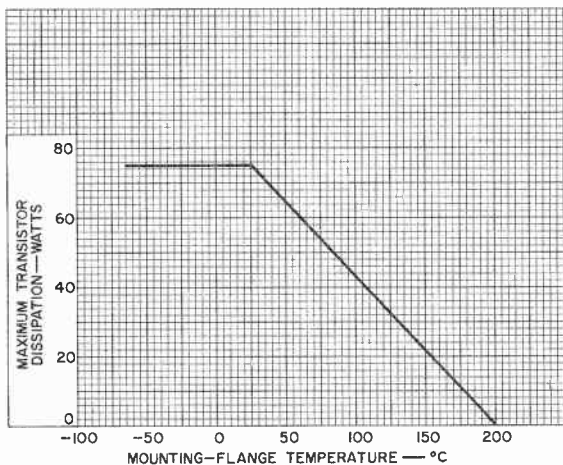
## ASSOCIATED WAVE FORMS



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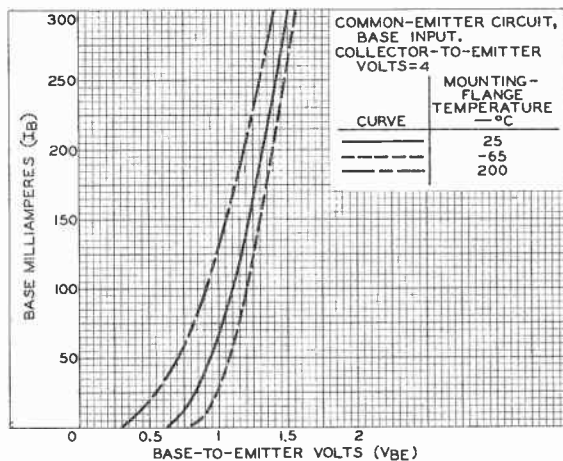


## RATING CHART



92CS-11088

## TYPICAL BASE CHARACTERISTICS



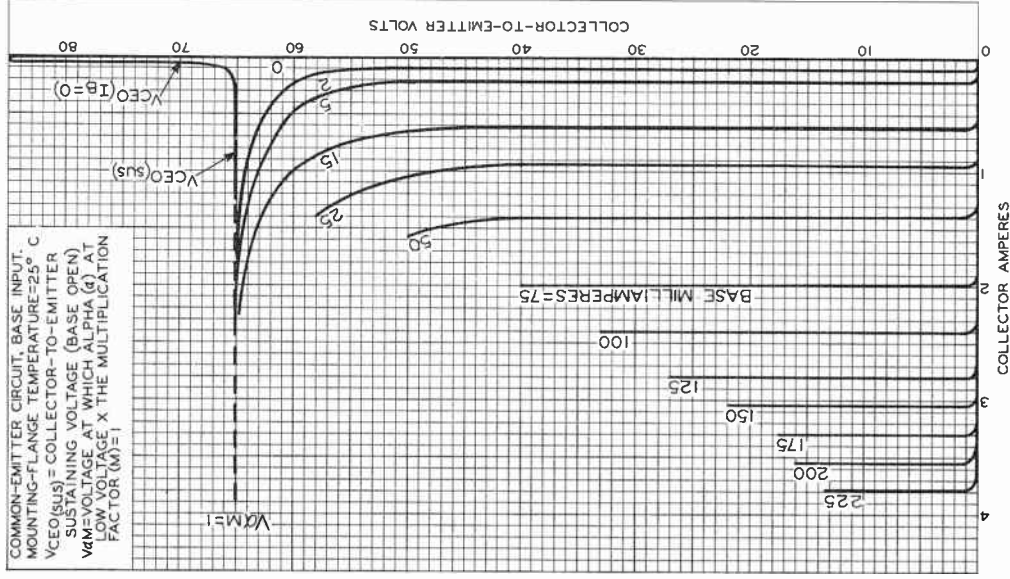
92CS-10451R2



# 2N1487

## TYPICAL COLLECTOR CHARACTERISTICS

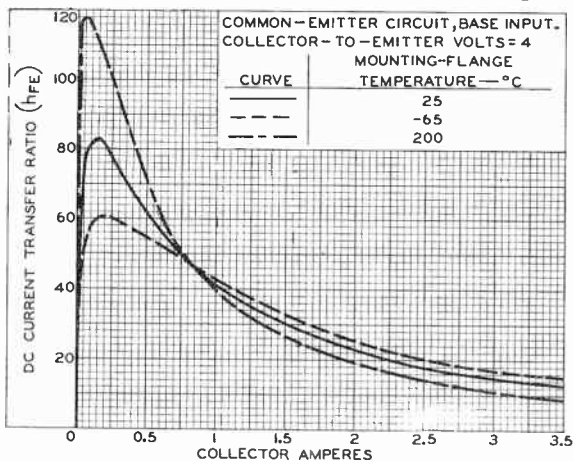
COMMON-EMITTER CIRCUIT, BASE INPUT.  
MOUNTING-FLANGE TEMPERATURE=25° C  
 $V_{CE0}(sus)$  = COLLECTOR-TO-EMITTER  
SUSTAINING VOLTAGE (BASE OPEN)  
 $V_{LM}$  = VOLTAGE AT WHICH ALPHA ( $\alpha$ ) AT  
LOW VOLTAGE X THE MULTIPLICATION  
FACTOR ( $M$ ) = 1



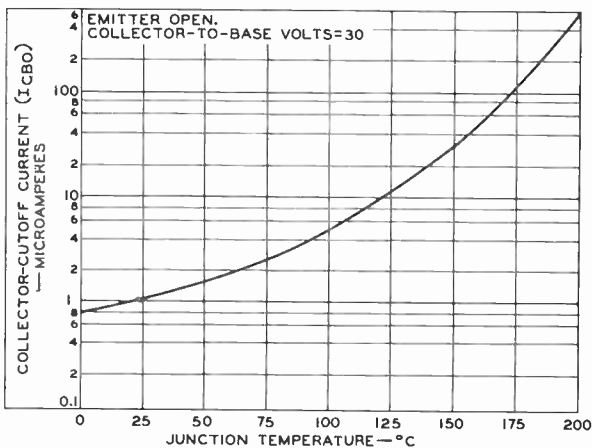
92CM-10447



## TYPICAL OPERATION CHARACTERISTICS



92CS-10454RI



92CS-10883







## Power Transistor

SILICON N-P-N DIFFUSED-JUNCTION TYPE  
 For Power Switching and Amplifier Service  
 in Industrial and Military Applications

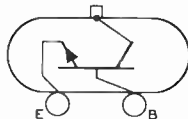
### GENERAL DATA

#### Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	0.865"
Maximum Seated Length. . . . .	0.390"
Maximum Length of Mounting Flange. . . . .	1.550"
Maximum Width of Mounting Flange. . . . .	1.015"
Case. . . . .	Metal
Mounting Flange. . . . .	Metal
Seals. . . . .	Hermetic
Socket. . . . .	Loranger Mfg. Corp. No. 2149, or equivalent

Terminal Diagram (See *Dimensional Outline*):

E - Emitter  
 B - Base



MOUNTING FLANGE-  
 Collector,  
 Case

### INDUSTRIAL SERVICE

*Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and servo-amplifier, relay- and solenoid-actuating circuits*

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	60 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE: . . . . .		
With emitter-to-base reverse biased (DC emitter-to-base volts = 1.5). . . . .	60 max.	volts
With base open (Sustaining voltage) <sup>a</sup> . . . . .	40 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	10 max.	volts
COLLECTOR CURRENT . . . . .	6 max.	amp
EMITTER CURRENT . . . . .	-8 max.	amp
BASE CURRENT. . . . .	3 max.	amp
TRANSISTOR DISSIPATION: <sup>b</sup>		
At mounting-flange temperature of 25° C . . . . .	75 max.	watts
At mounting-flange temperature of 100° C . . . . .	43 max.	watts
MOUNTING-FLANGE TEMPERATURE RANGE: <sup>c</sup>		
Operating and storage . . . . .	-65 to +200	°C

#### Characteristics:

*At mounting-flange temperature of 25° C<sup>c</sup>*

Alpha-Cutoff Frequency ( $f_{ab}$ ) with dc collector-to-base volts = 12, dc collector ma. = 100 . . . . .	1	Mc
--	---	----

← Indicates a change.



# 2N1489

Collector-to-Base Capacitance ( $C_{ob}$ )			
with dc collector-to-base volts = 40. . . . .	200	$\mu$ f	
Thermal Time Constant ( $\tau_1$ ). . . . .	12	msec	

## Typical Operation:

*In accompanying typical power-switching circuit at mounting-flange temperature of 25° C*

DC Supply Voltage ( $B_2$ ). . . . .	12	volts
DC Base-Bias Voltage ( $B_1$ ) . . . . .	-8.5	volts
"On" DC Collector Current . . . . .	1.5	amp
"Turn-On" Base Current ( $I_{B1}$ ). . . . .	0.3	amp
"Turn-Off" Base Current ( $I_{B2}$ ) . . . . .	-0.15	amp
Generator Resistance. . . . .	50	ohms
Switching Time:		
Delay Time ( $t_d$ ) . . . . .	0.2	$\mu$ sec
Rise Time ( $t_r$ ). . . . .	1	$\mu$ sec
Storage Time ( $t_s$ ) . . . . .	1	$\mu$ sec
Fall Time ( $t_f$ ). . . . .	1.2	$\mu$ sec

<sup>a</sup> The Collector-to-Emitter Sustaining voltage ( $V_{CE0(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{AM} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

<sup>b</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

<sup>c</sup> Measured at center of seating surface.

## CHARACTERISTICS RANGE VALUES FOR EQUIPMENT DESIGN

*Voltage values are given with respect to base and mounting-flange temperature<sup>c</sup> of 25° C unless otherwise specified*

	Min.	Max.	
Collector-to-Emitter Voltage:			
With emitter reverse bias			
volts = 1.5, dc collector			
ma. = 0.5. . . . .	$V_{CEX}$	60	- volts
With base open (Sustaining			
voltage), dc collector			
ma. = 100, dc base			
ma. = 0. . . . .	$V_{CE0}^a$	40	- volts
	(sus)		
Base-to-Emitter Voltage			
for dc collector-to-			
emitter volts = 4, dc			
collector amperes = 1.5. . .	$V_{BE}$	-	2.5 volts
Collector-Cutoff Current	$I_{CBO}$		
for dc collector volts =			
30, dc emitter ma. = 0,			
mounting-flange temperature =			
25° C. . . . .	-	25	$\mu$ a
150° C . . . . .	-	1000	$\mu$ a
Emitter-Cutoff Current for			
dc emitter volts = 10,			
dc collector ma. = 0. . . . .	$I_{EBO}$	-	25 $\mu$ a

→ Indicates a change.



DC Current Transfer Ratio for dc collector-to-emitter volts = 4, dc collector amperes = 1.5. . . . .	$h_{FE}$	25	75	
DC Collector-to-Emitter Saturation Resistance for dc collector amperes = 1.5, dc base ma. = 100. . . . .	$R_S$	-	0.67	ohms
Thermal Resistance: Junction-to-mounting-flange	$R_T$	-	2.33	°C/watt ←

<sup>a</sup> The Collector-to-Emitter Sustaining Voltage ( $V_{CE0(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{AM} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

<sup>c</sup> Measured at center of seating surface.

**OPERATING CONSIDERATIONS,  
TYPICAL POWER SWITCHING CIRCUIT,  
RATING CHART,  
and CURVES**

shown under Type 2N1487 also apply to the 2N1489

← indicates a change.





## Mesa Transistor

SILICON N-P-N DOUBLE-DIFFUSED-JUNCTION TYPE  
For Very High Frequency Amplifier and Oscillator  
Service in Industrial and Military Applications

## GENERAL DATA

## Mechanical:

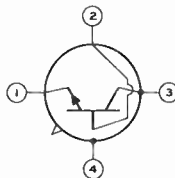
Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter . . . . .	0.370"
Dimensional Outline . . . . .	JEDEC No. TO-12
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	4
Minimum length . . . . .	0.500"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>

Terminal Diagram:

## BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base

Lead 3 - Collector,  
CaseLead 4 - Internally  
connected  
to case

## INDUSTRIAL SERVICE

*Such as large-signal power-amplifier,  
video-amplifier, and oscillator circuits*

## Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	30 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With emitter-to-base reverse biased . . . . .	30 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	1 max.	volt
COLLECTOR CURRENT . . . . .	50 max.	ma
EMITTER CURRENT . . . . .	-50 max.	ma
TRANSISTOR DISSIPATION (See <i>Rating Chart</i> ):		
Operation in free air:		
At ambient temperature of 25° C . . . . .	0.5 max.	watt
At ambient temperature of 100° C . . . . .	0.25 max.	watt
Operation with heat sink:		
At case temperature of 25° C . . . . .	3 max.	watts
At case temperature of 100° C . . . . .	1.5 max.	watts
AMBIENT-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +175	°C



# 2N1491

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base unless otherwise specified. Ambient temperature of 25° C.

Min. Typical Max.

DC Collector Breakdown Voltage for dc collector ma. = 0.1, dc emitter current = 0. . . . .	$BV_{CB0}$	30	-	-	volts
DC Emitter-Cutoff Current for dc emitter volts = 0.5, dc collector current = 0. . . . .	$I_{E0}$	-	-	100	$\mu a$
DC Collector-Cutoff Current for dc collector volts = 12, dc emitter current = 0. . . . .	$I_{C0}$	-	-	10	$\mu a$
Collector-to-Base and Stem Capacitance for dc col- lector volts = 30, dc emitter current = 0. . . . .		-	-	5	$\mu f$
Small-Signal Current Transfer Ratio: $h_{fe}$					
For dc collector-to- emitter volts = 20, dc collector ma. = 15, signal frequency of 1 kc. . . . .		15	50	200	
For dc collector-to- emitter volts = 30, dc collector ma. = 15, signal frequency of 100 Mc. . . . .		-	1.8	-	
Alpha-Cutoff Frequency for dc collector volts = 30, dc collector ma. = 15. . . . .	$f_{\alpha b}$	-	250	-	Mc
Power Gain at 70 Mc for dc collector volts = 20, dc emitter ma. = -15, power output (mw) = 10. . . . .	PG	13	15	-	db
→ Thermal Resistance: Junction-to-case . . . . .	$R_T$	-	-	50	°C/watt

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

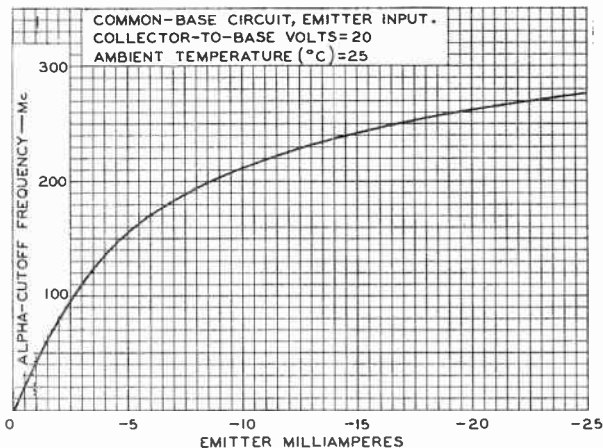
The flexible leads of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using this transistor, the temperature of the solder

→ Indicates a change.

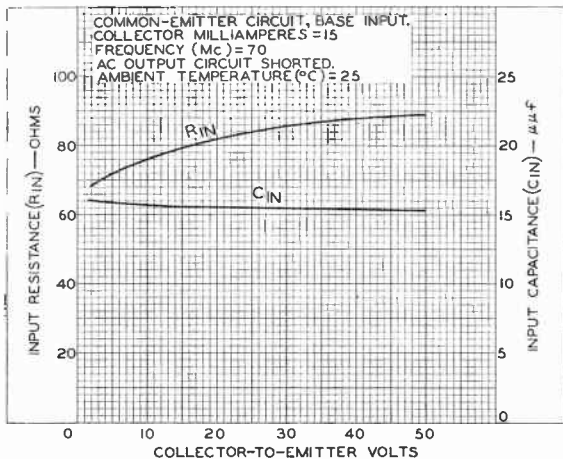


## TYPICAL CHARACTERISTIC



92CS-10510

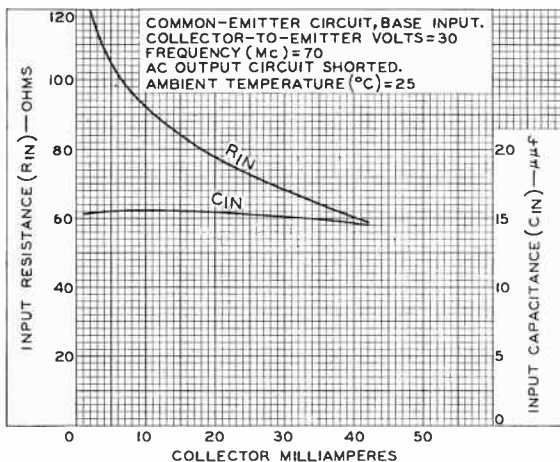
## PERFORMANCE CHARACTERISTICS



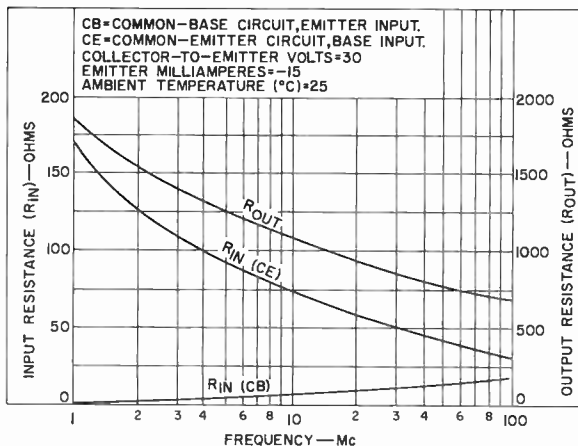
92CS-10523



## PERFORMANCE CHARACTERISTICS



92CS-10521

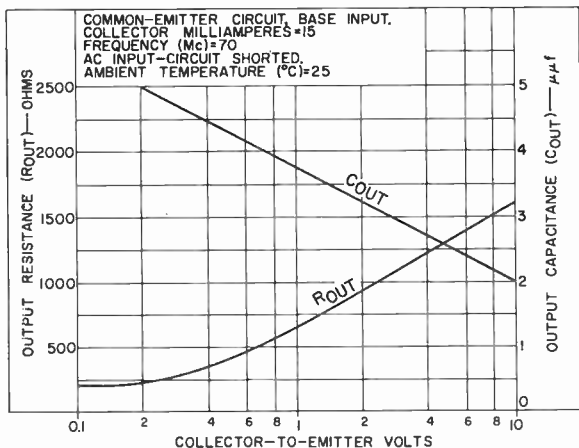


92CS-10514RI

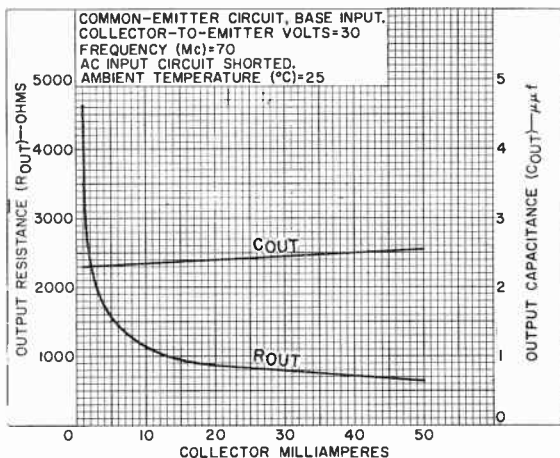




## PERFORMANCE CHARACTERISTICS



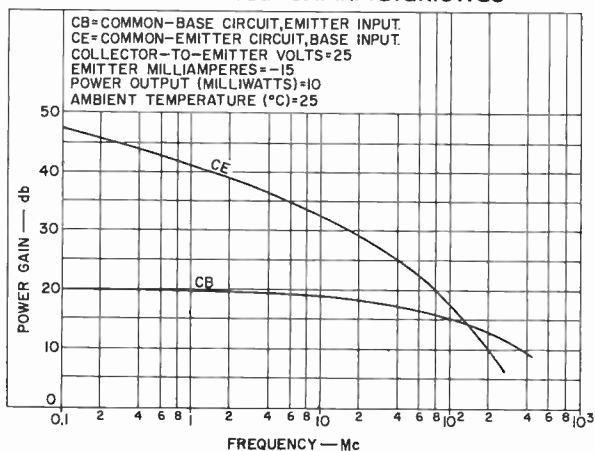
92CS-10513RI



92CS-10515RI



## PERFORMANCE CHARACTERISTICS



92CS-10517R1

## Mesa Transistor

SILICON N-P-N DOUBLE-DIFFUSED-JUNCTION TYPE  
For Very High Frequency Amplifier and Oscillator  
Service in Industrial and Military Applications

The 2N1492 is the same as the 2N1491 except for the following items:

## INDUSTRIAL SERVICE

Such as large-signal power-amplifier,  
video-amplifier, and oscillator circuits

Maximum Ratings, Absolute-Maximum Values:

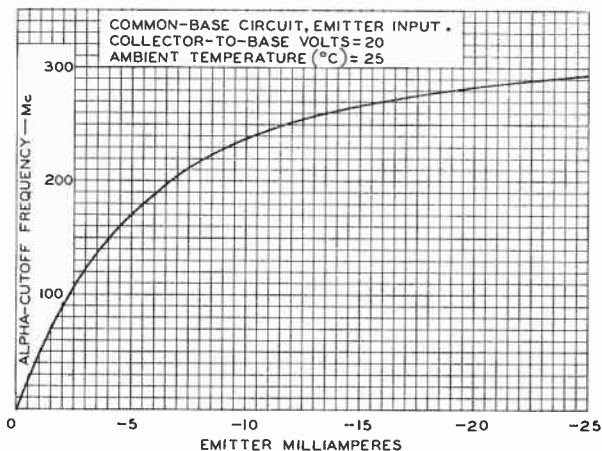
COLLECTOR-TO-BASE VOLTAGE. . . . .	60 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE: With emitter-to-base reverse biased. . . . .	60 max.	volts
EMITTER-TO-BASE VOLTAGE. . . . .	2 max.	volts

## ELECTRICAL CHARACTERISTICS

	Min.	Typical	Max.		
DC Collector Breakdown Voltage for dc collector ma. = 0.1, dc emitter current = 0. . . . .	$BV_{CBO}$	60	-	-	volts
Alpha-Cutoff Frequency for dc collector volts = 30, dc collector ma. = 15. . . . .	$f_{\alpha b}$	-	275	-	Mc
Power Gain at 70 Mc for dc collector volts = 30, dc emitter ma. = -15, power output (mw) = 100. . . . .	PG	13	15	-	db



## TYPICAL CHARACTERISTIC



92CS-10512



## Mesa Transistor

SILICON N-P-N DOUBLE-DIFFUSED-JUNCTION TYPE  
 For Very High Frequency Amplifier and Oscillator  
 Service in Industrial and Military Applications

The 2N1493 is the same as the 2N1491 except for the following items:

### INDUSTRIAL SERVICE

Such as large-signal power-amplifier,  
 video-amplifier, and oscillator circuits

Maximum Ratings, Absolute-Maximum Values:

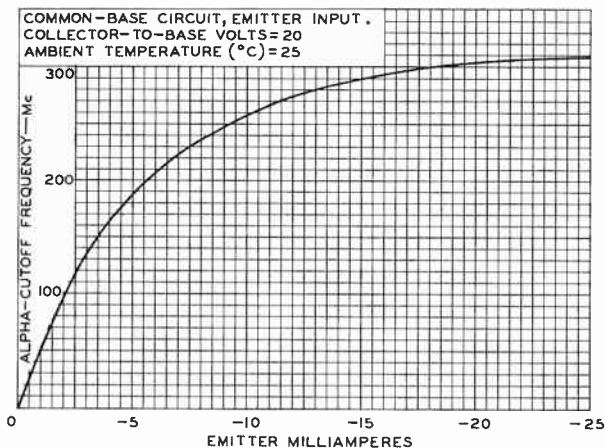
COLLECTOR-TO-BASE VOLTAGE. . . . .	100 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE With emitter-to-base reverse biased. . . . .	100 max.	volts
EMITTER-TO-BASE VOLTAGE. . . . .	4.5 max.	volts

### ELECTRICAL CHARACTERISTICS

	Min.	Typical	Max.	
DC Collector Breakdown Voltage for dc collector ma. = 0.1, dc emitter current = 0. . . . .	$BV_{CBO}$	100	-	- volts
Alpha-Cutoff Frequency for dc collector volts = 30, dc collector ma. = 15 . . . . .	$f_{\alpha b}$	-	300	- Mc
Power Gain at 70 Mc: For dc collector volts = 20, dc emitter ma. = -15, power output (mw) = 10 . . . . .		-	16	- db
For dc collector volts = 30, dc emitter ma. = -15, power output (mw) = 100 . . . . .		-	16	- db
For dc collector volts = 50, dc emitter ma. = -25, power output (mw) = 500 . . . . .		10	12	- db



## TYPICAL CHARACTERISTIC



92CS-10511

## Power Transistor

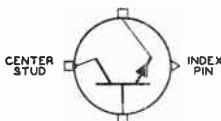
SILICON N-P-N DIFFUSED-JUNCTION TYPE  
For Power Switching and Amplifier Service  
in Industrial and Military Applications

## GENERAL DATA

## Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	1.230"
Maximum Seated Length. . . . .	0.520"
Maximum Diameter. . . . .	1.250"
Dimensional Outline. . . . .	JEDEC No. TO-36
Case. . . . .	Welded, Metal
Seals. . . . .	Hermetic
Terminal Diagram (See <i>Dimensional Outline</i> ):	

## BOTTOM VIEW



## INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and servo-amplifier, relay- and solenoid-actuating circuits

## Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	60 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With emitter-to-base reverse biased (DC emitter-to-base volts = 1.5). . . . .	60 max.	volts
With base open (Sustaining voltage) <sup>a</sup> . . . . .	40 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	10 max.	volts
COLLECTOR CURRENT . . . . .	6 max.	amp
EMITTER CURRENT . . . . .	-8 max.	amp
BASE CURRENT. . . . .	3 max.	amp
TRANSISTOR DISSIPATION: <sup>b</sup>		
At case temperature of 25° C. . . . .	75 max.	watts
At case temperature of 100° C. . . . .	43 max.	watts
CASE-TEMPERATURE RANGE: <sup>c</sup>		
Operating and storage . . . . .	-65 to +200	°C

## Characteristics:

At case temperature of 25° C<sup>c</sup>

Alpha-Cutoff Frequency ( $f_{\alpha b}$ ) with dc collector-to-base volts = 12, dc collector ma. = 100. . . . .	1	Mc
---	---	----

← Indicates a change.



# 2N1511

Collector-to-Base Capacitance ( $C_{ob}$ )			
with dc collector-to-base volts = 40. . . . .	200	$\mu\text{mf}$	
Thermal Time Constant ( $\tau_1$ ). . . . .	12	msec	

## Typical Operation:

*In accompanying typical power-switching circuit at case temperature<sup>c</sup> of 25° C*

DC Supply Voltage ( $B_2$ ). . . . .	12	volts
DC Base-Bias Voltage ( $B_1$ ) . . . . .	-8.5	volts
"On" DC Collector Current . . . . .	1.5	amp
"Turn-On" Base Current ( $I_{B1}$ ) . . . . .	0.3	amp
"Turn-Off" Base Current ( $I_{B2}$ ) . . . . .	-0.15	amp
Generator Resistance. . . . .	50	ohms
Switching Time:		
Delay time ( $t_d$ ) . . . . .	0.2	$\mu\text{sec}$
Rise time ( $t_r$ ) . . . . .	1	$\mu\text{sec}$
Storage time ( $t_s$ ) . . . . .	1	$\mu\text{sec}$
Fall time ( $t_f$ ) . . . . .	1.2	$\mu\text{sec}$

<sup>a</sup> The Collector-to-Emitter Sustaining voltage ( $V_{CE0(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $\alpha_{EM} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity.

<sup>b</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

<sup>c</sup> Measured at intersection of seating surface with the stud.

## CHARACTERISTICS RANGE VALUES FOR EQUIPMENT DESIGN

*Voltage values are given with respect to base and case temperature<sup>c</sup> of 25° C unless otherwise specified*

Min. Max.

Collector-to-Emitter Voltage:			
With emitter reverse-bias			
volts = 1.5, dc collector			
ma. = 0.5 . . . . .	$V_{CEX}$	60	- volts
With base open (Sustaining			
voltage), dc collector ma.			
= 100, dc base ma. = 0. . . . .	$V_{CE0}^a$	40	- volts
	(sus)		
Base-to-Emitter Voltage for			
dc collector-to-emitter volts			
= 4, dc collector amperes = 1.5 . . . . .	$V_{BE}$	-	3.5 volts
Collector-Cutoff Current			
for dc collector volts = 30,			
dc emitter ma. = 0, case	$I_{CBO}$		
temperature =			
25° C . . . . .		-	25 $\mu\text{a}$
150° C. . . . .		-	1000 $\mu\text{a}$
Emitter-Cutoff Current for dc			
emitter volts = 10, dc			
collector ma. = 0 . . . . .	$I_{EBO}$	-	25 $\mu\text{a}$
DC Current Transfer Ratio for dc			
collector-to-emitter volts = 4,			
dc collector amperes = 1.5 . . . . .	$h_{FE}$	15	45

→ Indicates a change.





## DC Collector-to-Emitter

Saturation Resistance for

dc collector amperes = 1.5,

dc base ma. = 300 . . . . .  $R_S$  - 2 ohms

Thermal Resistance:

Junction-to-case. . . . .  $R_T$  - 2.33 °C/watt ←

<sup>a</sup> The Collector-to-Emitter Sustaining Voltage ( $V_{CE0(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{OM} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

<sup>c</sup> Measured at intersection of seating surface with the stud.

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

Electrical connection can be made to the base and emitter terminals by means of clips or by soldering directly to the terminals. When soldering connections are made to the terminals, care should be taken to conduct excessive heat away from the terminal seals, otherwise the heat of the soldering operation will crack the glass seals of the terminals and damage the transistor.

This transistor is provided with a single-ended stud for mounting to a heat sink and for electrical connection to the collector. (See accompanying *Suggested Mounting Arrangement*). Electrical connection to the base and to the emitter is made to their respective terminals.

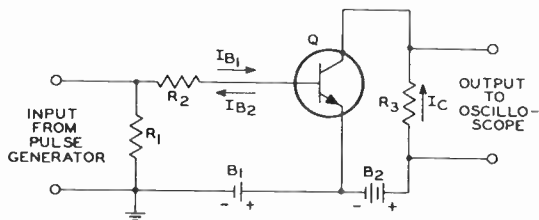
It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.

← Indicates a change.



# 2N1511

## TYPICAL POWER-SWITCHING CIRCUIT



92CS-10763

$B_1$ : 8.5 volts

$B_2$ : 12 volts

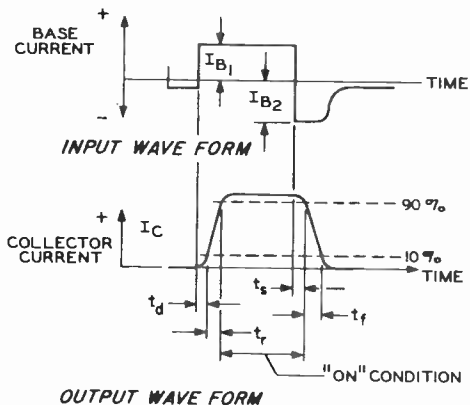
Q: Transistor type 2N1511

$R_1$ : 50 ohms, 1 watt

$R_2$ : 30 ohms, 1 watt

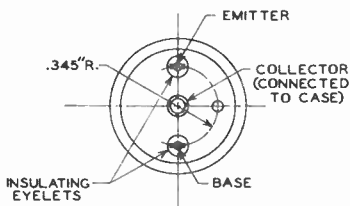
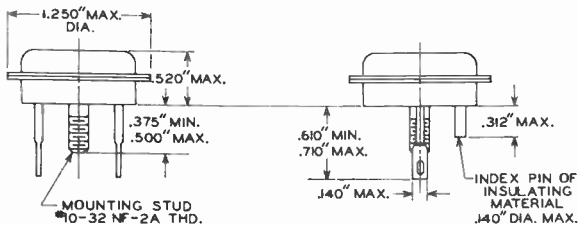
$R_3$ : 7.8 ohms, 2 watts

## ASSOCIATED WAVE FORMS



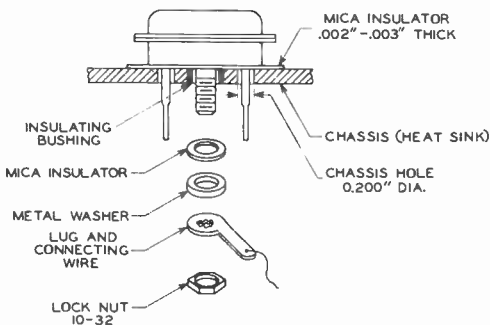
92CS-10029

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92CM-10612RI

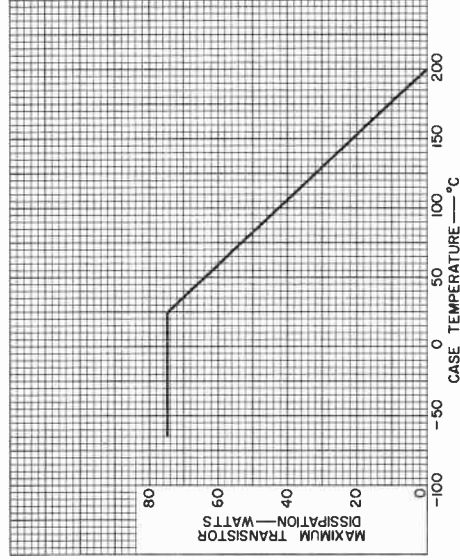
## SUGGESTED MOUNTING ARRANGEMENT



92CS-10624RI



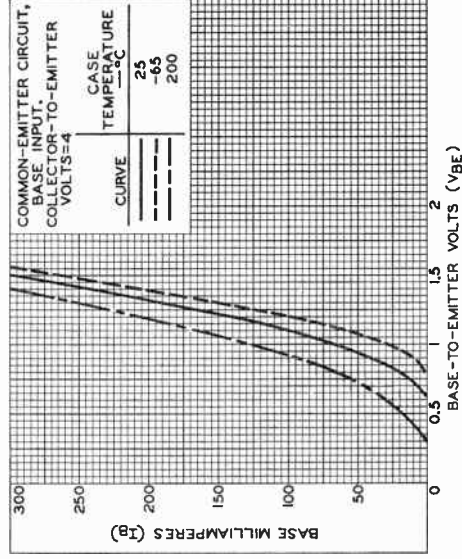
## RATING CHART



World Radio History

92CS-10769RI

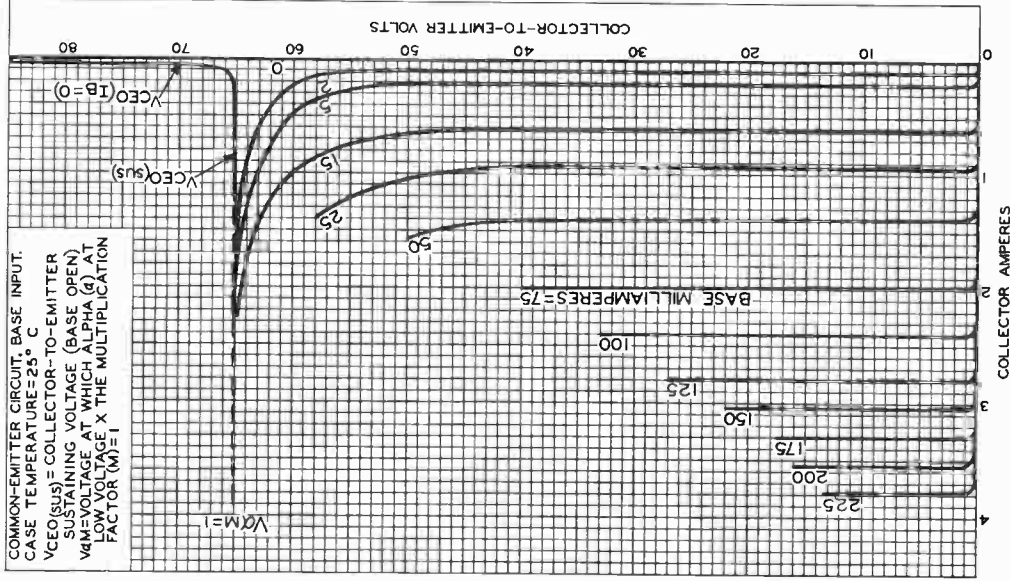
## TYPICAL BASE CHARACTERISTICS



92CS-10771RI

## TYPICAL COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT.  
 CASE TEMPERATURE = 25° C  
 $V_{CEO(sus)}$  = COLLECTOR-TO-EMITTER  
 SUSTAINING VOLTAGE (BASE OPEN)  
 $V_{\alpha M}$  = VOLTAGE AT WHICH ALPHA ( $\alpha$ ) AT  
 LOW VOLTAGE X THE MULTIPLICATION  
 FACTOR ( $M$ ) = 1

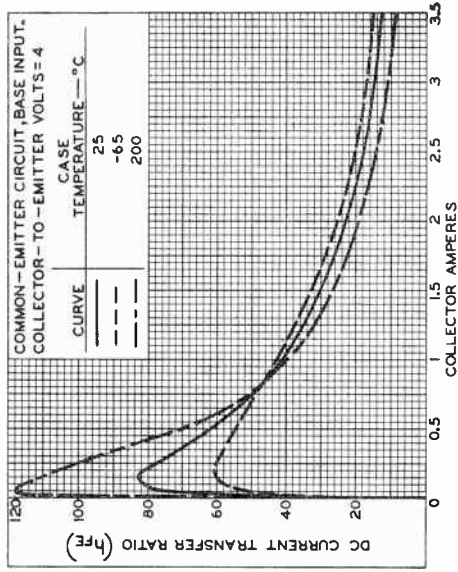


92CM-10773



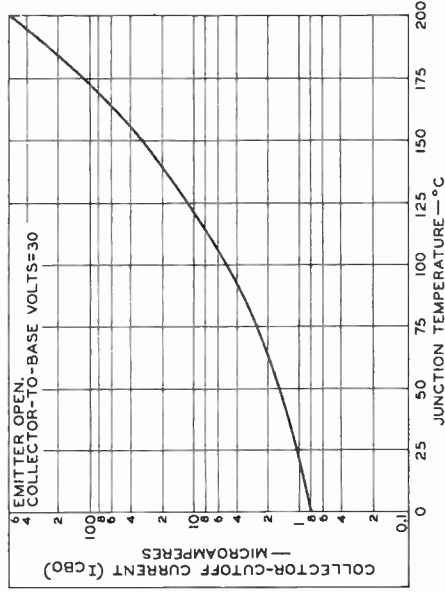
# 2N1511

## TYPICAL OPERATION CHARACTERISTICS



World Radio History

92CS-10772RI



92CS-10883

RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division

Somerville, N. J.



## Power Transistor

## SILICON N-P-N DIFFUSED-JUNCTION TYPE

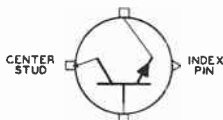
For High-Power Switching and Amplifier Service in Industrial and Military Applications

## GENERAL DATA

## Mechanical:

Operating Position . . . . .	Any
Maximum Overall Length . . . . .	1.230"
Maximum Seated Length . . . . .	0.520"
Maximum Diameter . . . . .	1.250"
Dimensional Outline . . . . .	JEDEC No. TO-36
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic
Terminal Diagram (See <i>Dimensional Outline</i> ):	

## BOTTOM VIEW



## INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and servo-amplifier, relay- and solenoid-actuating circuits

## Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	60 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With emitter-to-base reverse biased (DC emitter-to-base volts = 1.5) . . . . .	60 max.	volts
With base open (Sustaining voltage) <sup>†</sup> . . . . .	40 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	10 max.	volts
COLLECTOR CURRENT . . . . .	6 max.	amp
EMITTER CURRENT . . . . .	-8 max.	amp
BASE CURRENT . . . . .	3 max.	amp
TRANSISTOR DISSIPATION: <sup>*</sup>		
At case temperature of 25° C . . . . .	60 max.	watts
At case temperature of 100° C . . . . .	30 max.	watts
CASE-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +175	°C

## Characteristics:

At case temperature of 25° C

Alpha-Cutoff Frequency ( $f_{\alpha b}$ ) with dc collector-to-base volts = 12, dc collector ma. = 100 . . . . .	1	Mc
--	---	----



# 2N1511

Collector-to-Base Capacitance ( $C_{ob}$ )			
with dc collector-to-base volts = 40. . . . .	200		$\mu\mu\text{f}$
Thermal Time Constant ( $\tau_1$ ). . . . .	12		msec

## Typical Operation:

*In accompanying typical power-switching circuit at case temperature of 25° C*

DC Supply Voltage ( $B_2$ ). . . . .	12	volts
DC Base-Bias Voltage ( $B_1$ ) . . . . .	-8.5	volts
"On" DC Collector Current . . . . .	1.5	amp
"Turn-On" Base Current ( $I_{B1}$ ). . . . .	0.3	amp
"Turn-Off" Base Current ( $I_{B2}$ ) . . . . .	-0.15	amp
Generator Resistance. . . . .	50	ohms
Switching Time:		
Delay time ( $t_d$ ) . . . . .	0.2	$\mu\text{sec}$
Rise time ( $t_r$ ). . . . .	1	$\mu\text{sec}$
Storage time ( $t_s$ ) . . . . .	1	$\mu\text{sec}$
Fall time ( $t_f$ ). . . . .	1.2	$\mu\text{sec}$

▲ The Collector-to-Emitter Sustaining Voltage ( $V_{CEQ(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $\alpha_{eff} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity.

● See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## CHARACTERISTICS RANGE VALUES FOR EQUIPMENT DESIGN

*Voltage values are given with respect to base and case temperature of 25° C unless otherwise specified*

	Min.	Max.	
Collector-to-Emitter Voltage:			
With emitter reverse-bias volts = 1.5, dc collector ma. = 0.5 . . . . .	$V_{CEX}$	60	- volts
With base open (Sustaining voltage), dc collector ma. = 100, dc base ma. = 0. . . . .	$V_{CEQ(sus)}$	40	- volts
Base-to-Emitter Voltage for dc collector-to-emitter volts = 4, dc collector amperes = 1.5 . . . . .			
	$V_{BE}$	-	3.5 volts
Collector-Cutoff Current for dc collector volts = 30, dc emitter ma. = 0, case temperature =			
25° C . . . . .		-	25 $\mu\text{a}$
175° C. . . . .		-	1000 $\mu\text{a}$
Emitter-Cutoff Current for dc emitter volts = 10, dc collector ma. = 0 . . . . .			
	$I_{EBO}$	-	25 $\mu\text{a}$
DC Current Transfer Ratio for dc collector-to-emitter volts = 4, dc collector amperes = 1.5 . . . . .			
	$h_{FE}$	10	50





## DC Collector-to-Emitter

Saturation Resistance for

dc collector amperes = 1.5,

dc base ma. = 300 . . . . .  $R_S$  - 2 ohms

Thermal Resistance:

Junction-to-case. . . . .  $R_T$  - 2.5 °C/watt

- ▲ The Collector-to-Emitter Sustaining Voltage ( $V_{CE(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{\alpha M} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

Electrical connection can be made to the base and emitter terminals by means of clips or by soldering directly to the terminals. When soldering connections are made to the terminals, care should be taken to conduct excessive heat away from the terminal seals, otherwise the heat of the soldering operation will crack the glass seals of the terminals and damage the transistor.

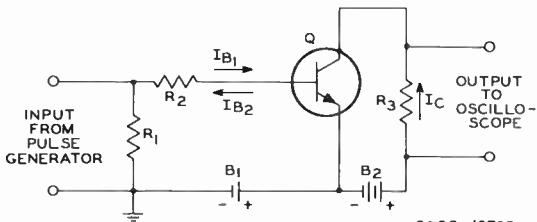
This transistor is provided with a single-ended stud for mounting to a heat sink and for electrical connection to the collector. (See *accompanying Suggested Mounting Arrangement*). Electrical connection to the base and to the emitter is made to their respective terminals.

It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.



# 2N1511

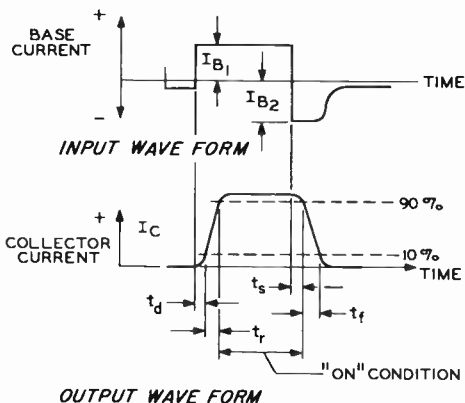
## TYPICAL POWER-SWITCHING CIRCUIT



92CS-10763

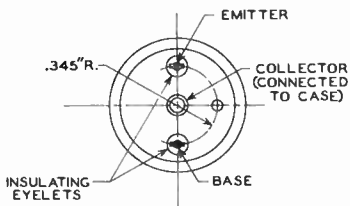
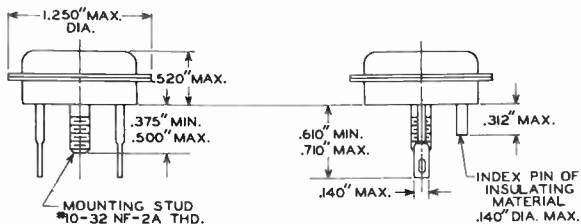
- $B_1$ : 8.5 volts
- $B_2$ : 12 volts
- Q: Transistor type 2N1511
- $R_1$ : 50 ohms, 1 watt
- $R_2$ : 30 ohms, 1 watt
- $R_3$ : 7.8 ohms, 2 watts

## ASSOCIATED WAVE FORMS



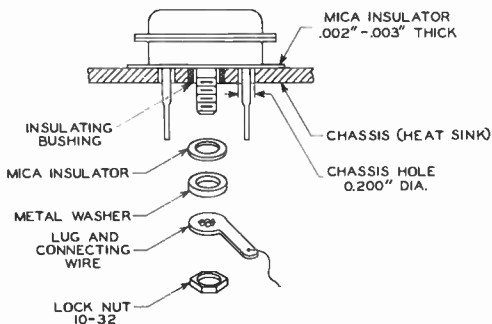
92CS-10029

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92CM-10612R1

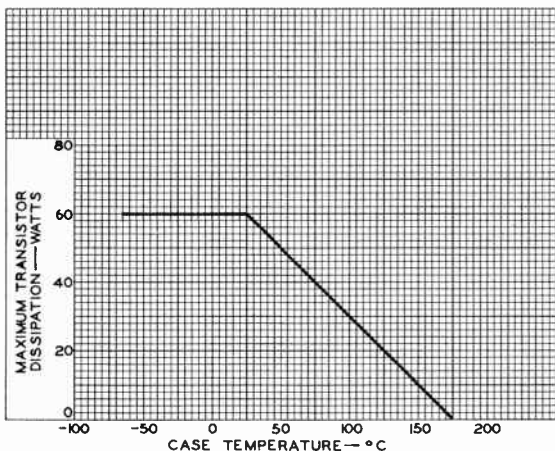
## SUGGESTED MOUNTING ARRANGEMENT



92CS-10624R1

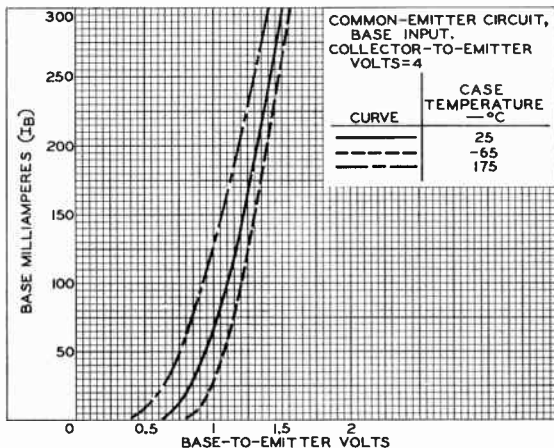


## RATING CHART



92CS-10769

## TYPICAL BASE CHARACTERISTICS



92CS-10771

## TYPICAL COLLECTOR CHARACTERISTICS

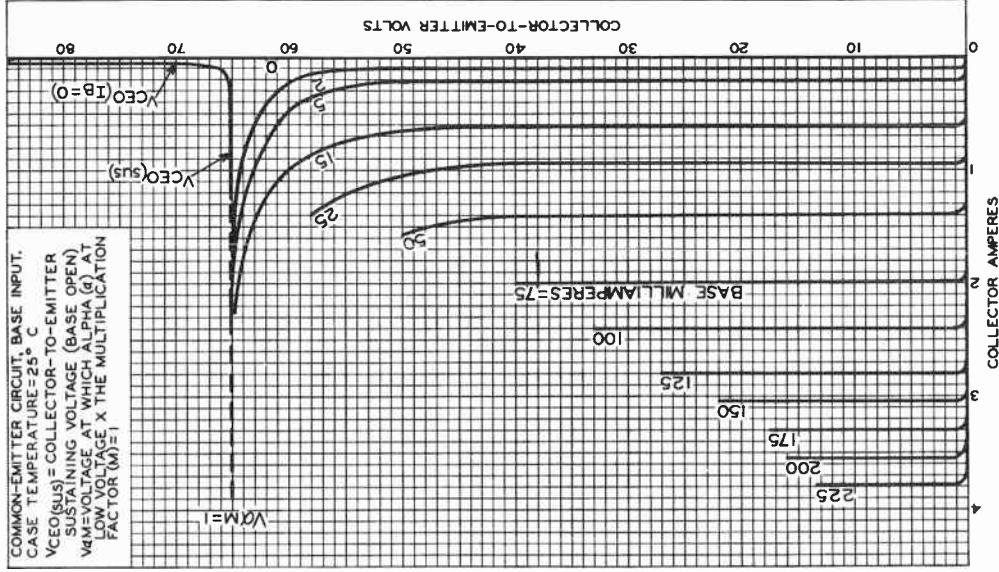
COMMON-EMITTER CIRCUIT, BASE INPUT,  
CASE TEMPERATURE = 25° C

$V_{CEO}(sus)$  = COLLECTOR-TO-EMITTER

SUSTAINING VOLTAGE (BASE OPEN)

$V_M$  = VOLTAGE AT WHICH ALPHA (g) AT  
LOW VOLTAGE X THE MULTIPLICATION

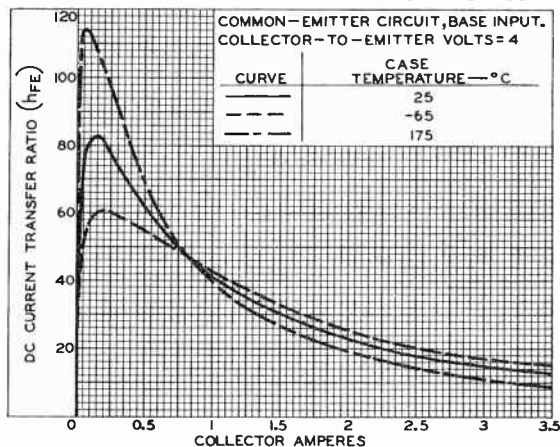
FACTOR (M) = 1



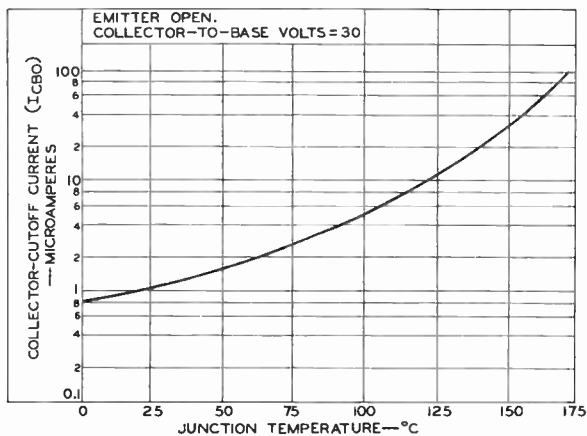
92CM-10773



## TYPICAL OPERATION CHARACTERISTICS



92CS-10772



92CS-10449

## Power Transistor

SILICON N-P-N DIFFUSED-JUNCTION TYPE  
For High-Power Switching and Amplifier Ser-  
vice in Industrial and Military Applications

The 2N1512 is the same as the 2N1511 except for the following items:

## INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and servo-amplifier, relay- and solenoid-actuating circuits

Maximum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	100 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With emitter-to-base reverse biased		
(DC emitter-to-base volts = 1.5). . . . .	100 max.	volts
With base open (Sustaining voltage) <sup>▲</sup> . . . . .	55 max.	volts

## CHARACTERISTICS RANGE VALUES FOR EQUIPMENT DESIGN

		Min.	Max.	
Collector-to-Emitter Voltage:				
With emitter reverse-bias				
volts = 1.5, dc collector				
ma. = 0.5 . . . . .	$V_{CEX}$	100	-	volts
With base open (Sustaining				
voltage), dc collector				
ma. = 100, dc base				
ma. = 0 . . . . .	$V_{CEO}^{\Delta}$	55	-	volts
	(sus)			

<sup>▲</sup> The Collector-to-Emitter Sustaining voltage ( $V_{CEO(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{CEM} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).







## Power Transistor

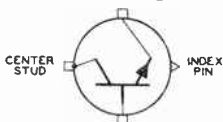
**SILICON N-P-N DIFFUSED-JUNCTION TYPE**  
**For Power Switching and Amplifier Service**  
**in Industrial and Military Applications**

### GENERAL DATA

#### Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	1.230"
Maximum Seated Length. . . . .	0.520"
Maximum Diameter. . . . .	1.250"
Dimensional Outline. . . . .	JEDEC No. TO-36
Case. . . . .	Welded, Metal
Seals. . . . .	Hermetic
Terminal Diagram (See <i>Dimensional Outline</i> ):	

BOTTOM VIEW



### INDUSTRIAL SERVICE

*Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and servo-amplifier, relay- and solenoid-actuating circuits*

#### Maximum and Minimum Ratings, Absolute Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	60 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With emitter-to-base reverse biased		
(DC emitter-to-base volts = 1.5). . . . .	60 max.	volts
with base open (Sustaining voltage) <sup>a</sup> . . . . .	40 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	10 max.	volts
COLLECTOR CURRENT . . . . .	6 max.	amp
EMITTER CURRENT . . . . .	-8 max.	amp
BASE CURRENT. . . . .	3 max.	amp
TRANSISTOR DISSIPATION: <sup>b</sup>		
At case temperature of 25° C. . . . .	75 max.	watts
At case temperature of 100° C. . . . .	43 max.	watts
CASE-TEMPERATURE RANGE: <sup>c</sup>		
Operating and storage . . . . .	-65 to +200	°C

#### Characteristics:

*At case temperature of 25° C°*

Alpha-Cutoff Frequency ( $f_{\alpha b}$ ) with dc collector-to-base volts = 12, dc collector ma. = 100 . . . . .	1	Mc
Collector-to-Base Capacitance ( $C_{ob}$ ) with dc collector-to-base volts = 40. . . . .	200	$\mu\text{mf}$
Thermal Time Constant ( $\tau_1$ ). . . . .	12	msec

← Indicates a change.



# 2N1513

## Typical Operation:

In accompanying typical power switching circuit at case temperature<sup>c</sup> of 25° C

DC Supply Voltage ( $B_2$ ) . . . . .	12	volts
DC Base-Bias Voltage ( $B_1$ ) . . . . .	-8.5	volts
"On" DC Collector Current . . . . .	1.5	amp
"Turn-On" Base Current ( $I_{B1}$ ) . . . . .	0.3	amp
"Turn-Off" Base Current ( $I_{B2}$ ) . . . . .	-0.15	amp
Generator Resistance . . . . .	50	ohms
Switching Time:		
Delay time ( $t_d$ ) . . . . .	0.2	$\mu$ sec
Rise time ( $t_r$ ) . . . . .	1	$\mu$ sec
Storage time ( $t_s$ ) . . . . .	1	$\mu$ sec
Fall time ( $t_f$ ) . . . . .	1.2	$\mu$ sec

<sup>a</sup> The collector-to-emitter sustaining voltage ( $V_{CE0(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{\alpha M} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage times the multiplication factor ( $M$ ) equals unity).

<sup>b</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

<sup>c</sup> Measured at intersection of seating surface with the stud.

## CHARACTERISTICS RANGE VALUES FOR EQUIPMENT DESIGN

Voltage values are given with respect to base and case temperature<sup>c</sup> of 25° C unless otherwise specified

Min. Max.

### Collector-to-Emitter Voltage:

With emitter reverse-bias  
volts = 1.5, dc collector

ma. = 0.5 . . . . .  $V_{CEX}$  60 - volts

With base open (Sustaining  
voltage), dc collector

ma. = 100, dc base  
ma. = 0 . . . . .  $V_{CE0(sus)}^a$  40 - volts

### Base-to-Emitter Voltage

for dc collector-to-  
emitter volts = 4, dc

collector amperes = 1.5 . . . . .  $V_{BE}$  - 2.5 volts

### → Collector-Cutoff Current

for dc collector volts =  
30, dc emitter ma. = 0,

case temperature =

25° C . . . . . - 25  $\mu$ a

150° C . . . . . - 1000  $\mu$ a

### Emitter-Cutoff Current for dc emitter volts = 10,

dc collector ma. = 0 . . . . .  $I_{EBO}$  - 25  $\mu$ a

### DC Current Transfer Ratio for dc collector-to-emitter

volts = 4, dc collector  
amperes = 1.5 . . . . .  $h_{FE}$  25 75

→ Indicates a change.



## DC Collector-to-Emitter

Saturation Resistance for

dc collector amperes = 1.5,

dc base ma. = 100. . . . .  $R_S$ 

- 0.67 ohms ←

Thermal Resistance:

Junction-to-case . . . . .  $R_T$ 

- 2.33 °C/watt

<sup>a</sup> The collector-to-emitter sustaining voltage ( $V_{CEQ(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{\alpha M} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

<sup>c</sup> Measured at intersection of seating surface with the stud.

OPERATING CONSIDERATIONS,  
TYPICAL POWER SWITCHING CIRCUIT,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHART,  
and CURVES,

shown under Type 2N1511 also apply to the 2N1513

← Indicates a change.





## Power Transistor

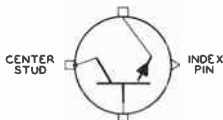
SILICON N-P-N DIFFUSED-JUNCTION TYPE  
For High-Power Switching and Amplifier Service  
in Industrial and Military Applications

## GENERAL DATA

## Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	1.230"
Maximum Seated Length. . . . .	0.520"
Maximum Diameter. . . . .	1.250"
Dimensional Outline. . . . .	JEDEC No. TO-36
Case. . . . .	Welded, Metal
Seals. . . . .	Hermetic
Terminal Diagram (See <i>Dimensional Outline</i> ):	

## BOTTOM VIEW



## INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and servo-amplifier, relay- and solenoid-actuating circuits

## Maximum and Minimum Ratings, Absolute Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	60 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE: With emitter-to-base reverse biased (DC emitter-to-base volts = 1.5). . . . .	60 max.	volts
With base open (Sustaining voltage)▲. . . . .	40 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	10 max.	volts
COLLECTOR CURRENT . . . . .	6 max.	amp
EMITTER CURRENT . . . . .	-8 max.	amp
BASE CURRENT. . . . .	3 max.	amp
TRANSISTOR DISSIPATION:● At case temperature of 25° C. . . . .	60 max.	watts
At case temperature of 100° C. . . . .	30 max.	watts
CASE-TEMPERATURE RANGE: Operating and storage . . . . .	-65 to +175	°C

## Characteristics:

At case temperature of 25° C

Alpha-Cutoff Frequency ( $f_{ab}$ ) with dc collector-to-base volts = 12, dc collector ma. = 100 . . . . .	1	Mc
Collector-to-Base Capacitance ( $C_{ob}$ ) with dc collector-to-base volts = 40. . . . .	200	$\mu$ f
Thermal Time Constant ( $\tau_1$ ). . . . .	12	msec



# 2N1513

## Typical Operation:

*In accompanying typical power switching circuit at case temperature of 25° C*

DC Supply Voltage ( $B_2$ ) . . . . .	12	volts
DC Base-Bias Voltage ( $B_1$ ) . . . . .	-8.5	volts
"On" DC Collector Current . . . . .	1.5	amp
"Turn-On" Base Current ( $I_{B1}$ ) . . . . .	0.3	amp
"Turn-Off" Base Current ( $I_{B2}$ ) . . . . .	-0.15	amp
Generator Resistance . . . . .	50	ohms
Switching Time:		
Delay time ( $t_d$ ) . . . . .	0.2	$\mu$ sec
Rise time ( $t_r$ ) . . . . .	1	$\mu$ sec
Storage time ( $t_s$ ) . . . . .	1	$\mu$ sec
Fall time ( $t_f$ ) . . . . .	1.2	$\mu$ sec

▲ The collector-to-emitter Sustaining voltage ( $V_{CEO(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $\alpha_M = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage times the multiplication factor ( $M$ ) equals unity).

● See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## CHARACTERISTICS RANGE VALUES FOR EQUIPMENT DESIGN

*Voltage values are given with respect to base and case temperature of 25° C unless otherwise specified*

	Min.	Max.	
Collector-to-Emitter Voltage:			
With emitter reverse-bias volts = 1.5, dc collector ma. = 0.5 . . . . . $V_{CEX}$	60	-	volts
With base open (Sustaining voltage), dc collector ma. = 100, dc base ma. = 0 . . . . . $V_{CEO(sus)}^{\Delta}$	40	-	volts
Base-to-Emitter Voltage for dc collector-to- emitter volts = 4, dc collector amperes = 1.5 . . . $V_{BE}$	-	2.5	volts
Collector-Cutoff Current for dc collector volts = 30, dc emitter ma. = 0, case temperature = 25° C . . . . .	-	25	$\mu$ a
175° C . . . . .	-	1000	$\mu$ a
Emitter-Cutoff Current for dc emitter volts = 10, dc collector ma. = 0 . . . . $I_{EBO}$	-	25	$\mu$ a
DC Current Transfer Ratio for dc collector-to-emitter volts = 4, dc collector amperes = 1.5 . . . . . $h_{FE}$	25	75	



## DC Collector-to-Emitter

Saturation Resistance for

dc collector amperes = 1.5,

dc base ma. = 100. . . . .  $R_S$  - 0.67 ohms

Thermal Resistance:

Junction-to-case . . . . .  $R_T$  - 2.5 °C/watt

- ▲ The Collector-to-Emitter Sustaining Voltage ( $V_{CE0(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{\alpha M} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

OPERATING CONSIDERATIONS,  
TYPICAL POWER SWITCHING CIRCUIT,  
DIMENSIONAL OUTLINE,  
SUGGESTED MOUNTING ARRANGEMENT,  
RATING CHART,  
and CURVES,

shown under Type 2N1511 also apply to the 2N1513







## Power Transistor

## SILICON N-P-N DIFFUSED-JUNCTION TYPE

For High-Power Switching and Amplifier Service in Industrial and Military Applications

The 2N1514 is the same as the 2N1513 except for the following items:

## INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and servo-amplifier, relay- and solenoid-actuating circuits

## Maximum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	100 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With emitter-to-base reverse biased		
(DC emitter-to-base volts = 1.5) . . . . .	100 max.	volts
With base open (Sustaining voltage) <sup>▲</sup> . . . . .	55 max.	volts

## CHARACTERISTICS RANGE VALUES FOR EQUIPMENT DESIGN

	Min.	Max.	
Collector-to-Emitter Voltage:			
With emitter reverse-bias			
volts = 1.5, dc collector			
ma. = 0.5 . . . . .	$V_{CEX}$	100	- volts
With base open (Sustaining			
voltage), dc collector			
ma. = 100, dc base			
ma. = 0 . . . . .	$V_{CEO}^{\Delta}$ (sus)	55	- volts

<sup>▲</sup> The Collector-to-Emitter Sustaining Voltage ( $V_{CEO(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{\alpha M} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).





## Drift-Field Transistor

## GERMANIUM P-N-P ALLOY TYPE

For Intermediate-Frequency-Amplifier Applications in Battery-Operated AM Radio Receivers

## GENERAL DATA

## Electrical:

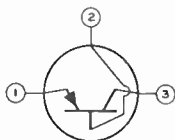
Minimum DC Collector-to-Base Voltage for dc emitter-to-base volts = -0.5, dc collector $\mu$ a = -50, ambient temperature = 25° C. . . . .	-24	volts
Maximum DC Collector-Cutoff Current ( $I_{CBO}$ ) for dc collector-to-base volts = -12, emitter open, ambient temperature = 25° C. . . . .	-16	$\mu$ a
Maximum DC Emitter-Cutoff Current ( $I_{EBO}$ ) for dc emitter-to-base volts = -0.5, collector open, ambient temperature = 25° C. . . . .	-16	$\mu$ a
Junction-Temperature Rise (In free air). . . . .	0.4	°C/mw

## Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads). . . . .	0.410"
Maximum Diameter . . . . .	0.240"
Dimensional Outline. . . . .	JEDEC No. TO-1
Case . . . . .	Metal
Seals. . . . .	Hermetic
Leads, Flexible. . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See Dimensional Outline
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base



Lead 3 - Collector  
(Adjacent  
to red dot  
on side of  
case)

## INTERMEDIATE-FREQUENCY AMPLIFIER

Maximum and Minimum Ratings, Absolute-Maximum Values:

DC COLLECTOR-TO-BASE VOLTAGE. . . . .	-24 max.	volts
DC EMITTER-TO-BASE VOLTAGE. . . . .	-0.5 max.	volt
DC COLLECTOR CURRENT. . . . .	-10 max.	ma
DC EMITTER CURRENT. . . . .	10 max.	ma
TRANSISTOR DISSIPATION:		
At ambient temperature of 25° C . . . . .	80 max.	mw
At ambient temperature of 55° C . . . . .	50 max.	mw
At ambient temperature of 71° C . . . . .	35 max.	mw
AMBIENT TEMPERATURE (During operation). . . . .	71 max.	°C
STORAGE-TEMPERATURE RANGE . . . . .	-65 to +85	°C



# 2N1524

Characteristics, At Ambient Temperature of 25° C:

*Common-Emitter Circuit, Base Input*

DC Collector-to-Emitter Voltage . . . . .	-12	volts
DC Emitter Current . . . . .	1	ma
Small-Signal Current Transfer Ratio at 1 kc. . . . .	60	

*Common-Base Circuit, Emitter Input*

DC Collector-to-Base Voltage . . . . .	-12	volts
DC Emitter Current . . . . .	1	ma
Small-Signal Current Transfer Ratio at 1 kc. . . . .	0.983	
Alpha-Cutoff Frequency . . . . .	33	Mc

Typical Operation: At Ambient Temperature of 25° C:

*In a common-emitter, base input, single-stage, 455-kc intermediate-frequency amplifier circuit*

DC Supply Voltage . . . . .	-6	-9	-12	volts
DC Collector-to-Emitter Voltage . . . . .	-5.7	-8.5	-11	volts
DC Emitter Current . . . . .	1	1	1	ma
Input Resistance . . . . .	1300	1350	1550	ohms
Output Resistance . . . . .	0.31	0.415	0.525	megohm
Collector-to-Base Capacitance (C <sub>ob</sub> ) . . . . .	2.2 <sup>▲</sup>	2.1 <sup>▲</sup>	2 <sup>▲</sup>	μmf
Maximum Power Gain* . . . . .	51	52.4	54.4	db
Useful Power Gain:				
In neutralized circuit . . . . .	33	33	33	db
In unneutralized circuit . . . . .	29.7	30	30.2	db

*In a common-emitter, base input, two-stage, 455-kc intermediate-frequency amplifier circuit*

DC Supply Voltage . . . . .	-6	-6	-9	-9	-12	-12	volts
DC Collector-to-Emitter Voltage . . . . .	-5.7	-5.7	-8.5	-8.5	-11	-11	volts
DC Emitter Current . . . . .	1	0.65	1	0.65	1	0.65	ma
Input Resistance . . . . .	1300	2100	1350	2200	1550	2500	ohms
Output Resistance . . . . .	0.31	0.49	0.415	0.65	0.525	0.82	megohm
Collector-to-Base Capacitance (C <sub>ob</sub> ) . . . . .	2.2 <sup>▲</sup>	2.2 <sup>▲</sup>	2.1 <sup>▲</sup>	2.1 <sup>▲</sup>	2 <sup>▲</sup>	2 <sup>▲</sup>	μmf
Maximum Power Gain* . . . . .	50.9	51.3	52.4	52.8	54	54.3	db
Useful Power Gain:							
In neutralized circuit . . . . .	31.2	30	31.2	30	31.2	30	db
In unneutralized circuit . . . . .	28.1	26.6	28.2	26.7	28.3	26.8	db

<sup>▲</sup> Maximum variation from this value is 1.4 μmf.

\* Measured in a single-tuned unilateralized circuit matched to the generator and load impedance for maximum transfer of power (transformer-insertion losses not included).



## OPERATING CONSIDERATIONS

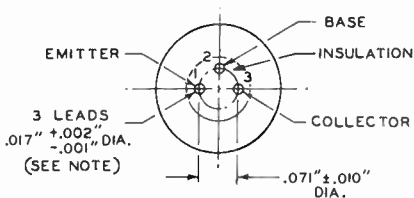
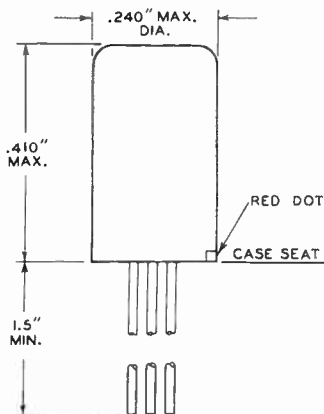
It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using this transistor, the temperature of the solder should not exceed 255° C for a maximum immersion period of 10 seconds.



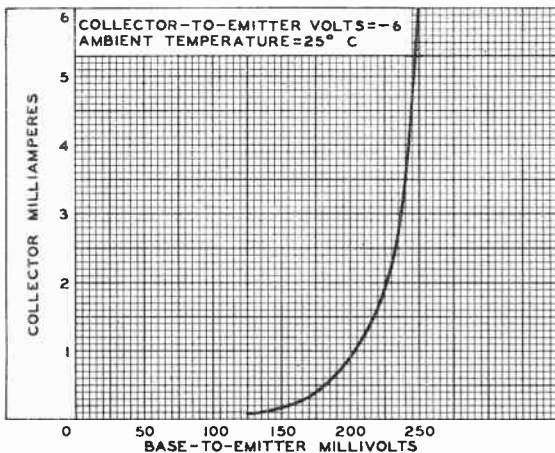
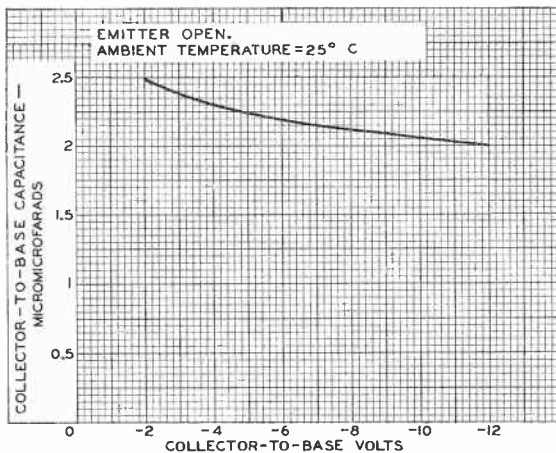
# 2N1524



92CS-9148R6

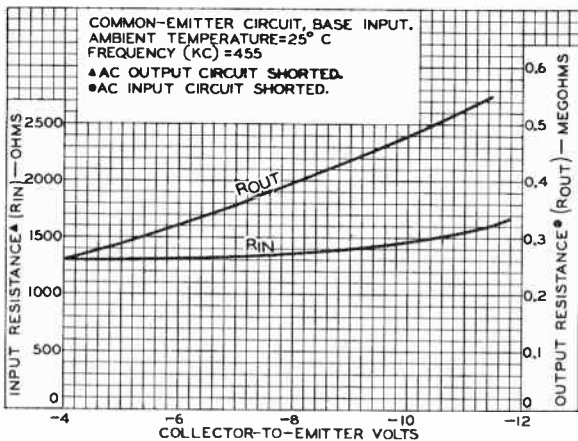
NOTE: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE CASE SEAT. BETWEEN 0.25" AND 1.5", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

## TYPICAL CHARACTERISTICS



# 2N1524

## TYPICAL CHARACTERISTICS



92CS-10770





## Drift-Field Transistor

### GERMANIUM P-N-P ALLOY TYPE

For Intermediate-Frequency-Amplifier Applications in Battery-Operated AM Radio Receivers

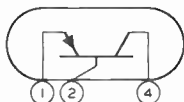
The 2N1525 is the same as the 2N1524 except for the following items:

#### Mechanical:

Maximum Overall Length . . . . .	0.697"
Maximum Seated Length . . . . .	0.495"
Maximum Diameter . . . . .	0.260"
Dimensional Outline . . . . .	JEDEC No. TO-40
Case . . . . .	Metal and Plastic

Terminal Diagram:

Pin 1 - Emitter  
Pin 2 - Base



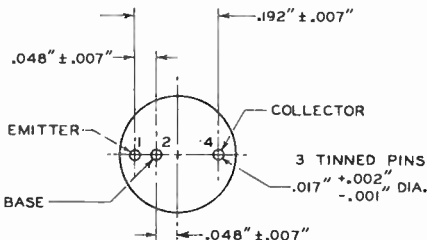
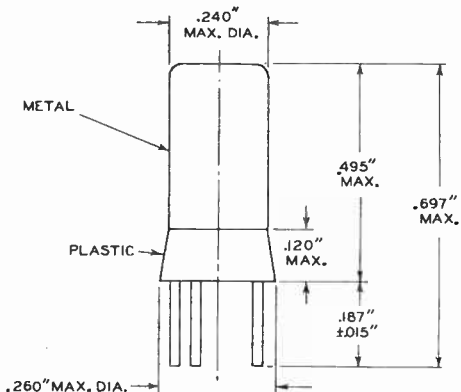
Pin 4 - Collector

### OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.



# 2N1525



PIN-SPACING TOLERANCES ARE NOT CUMULATIVE

92CS-8550R7

## Drift-Field Transistor

GERMANIUM P-N-P ALLOY TYPE  
For Converter Applications in  
Battery-Operated AM Radio Receivers

## GENERAL DATA

## Electrical:

Minimum DC Collector-to-Base Voltage for dc emitter-to-base volts = -0.5, dc collector $\mu a = -50$ , ambient temperature = 25° C. . . . .	-24	volts
Maximum DC Collector-Cutoff Current ( $I_{CBO}$ ) for dc collector-to-base volts = -12, emitter open, ambient temperature = 25° C. . . . .	-16	$\mu a$
Maximum DC Emitter-Cutoff Current ( $I_{EBO}$ ) for dc emitter-to-base volts = -0.5, collector open, ambient temperature = 25° C. . . . .	-16	$\mu a$
Junction-Temperature Rise (In free air). . . . .	0.4	°C/mv

## Mechanical:

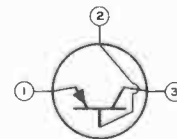
Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads). . . . .	0.410"
Maximum Diameter . . . . .	0.240"
Dimensional Outline. . . . .	JEDEC No. TO-1
Case . . . . .	Metal
Seals. . . . .	Hermetic
Leads, Flexible. . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>

Terminal Diagram:

BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base



Lead 3 - Collector  
(Adjacent to red dot on side of case)

## CONVERTER

Maximum and Minimum Ratings, *Absolute-Maximum Values:*

DC COLLECTOR-TO-BASE VOLTAGE. . . . .	-24 max.	volts
DC EMITTER-TO-BASE VOLTAGE. . . . .	-0.5 max.	volt
DC COLLECTOR CURRENT. . . . .	-10 max.	ma
DC EMITTER CURRENT. . . . .	10 max.	ma



# 2N1526

## TRANSISTOR DISSIPATION:

At ambient temperature of 25° C. . . . .	80 max.	mw
At ambient temperature of 55° C. . . . .	50 max.	mw
At ambient temperature of 71° C. . . . .	35 max.	mw
AMBIENT TEMPERATURE (During operation) . . .	71 max.	°C
STORAGE-TEMPERATURE RANGE. . . . .	-65 to +85	°C

## Characteristics, At Ambient Temperature of 25° C:

### Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage. . . . .	-12	volts
DC Emitter Current . . . . .	1	ma
Small-Signal Current Transfer Ratio at 1 kc. .	130	

### Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage . . . . .	-12	volts
DC Emitter Current . . . . .	1	ma
Small-Signal Current Transfer Ratio at 1 kc. .	0.992	
Alpha-Cutoff Frequency . . . . .	33	Mc

## Typical Operation, At Ambient Temperature of 25° C:

### In a common-emitter, base input, self-excited, 1.5 Mc-converter circuit

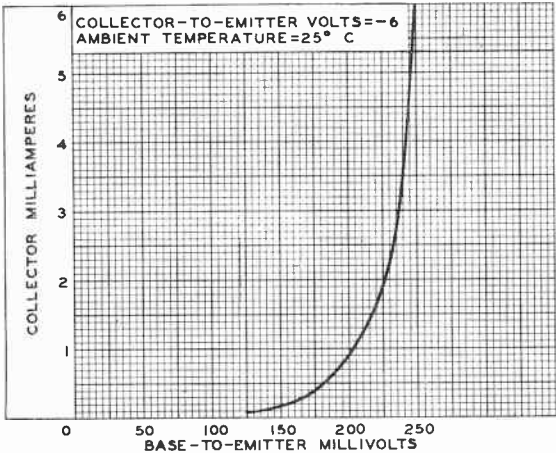
DC Supply Voltage. . . . .	-6	-9	-12	volts
DC Collector-to-Emitter Voltage. . . . .	-5	-8	-11	volts
DC Emitter Current . . . . .	0.65	0.65	0.65	ma
Input Resistance . . . . .	1850	1950	2150	ohms
Output Resistance. . . . .	0.19	0.28	0.48	megohm
RMS Base-to-Emitter Oscillator-Injection Voltage	100	100	100	mv
Conversion Power Gain:				
Maximum available. . . . .	44.2	46.1	48.9	db
Useful . . . . .	34.2	34.5	35.8	db

## OPERATING CONSIDERATIONS and DIMENSIONAL OUTLINE

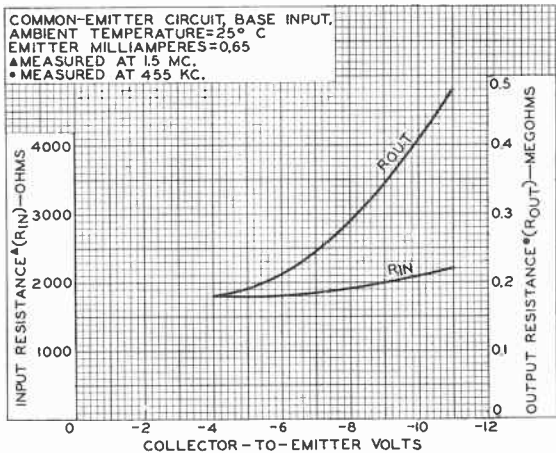
shown under Type 2N1524 also apply to the 2N1526



## TYPICAL CHARACTERISTICS



92CS-10679



92CS-10583RI





## Drift-Field Transistor

GERMANIUM P-N-P ALLOY TYPE

For Converter Applications in  
Battery-Operated AM Radio Receivers

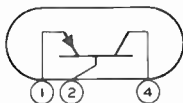
The 2N1527 is the same as the 2N1526 except for the following items:

### Mechanical:

Maximum Length . . . . .	0.697"
Maximum Seated Length . . . . .	0.495"
Maximum Diameter . . . . .	0.260"
Dimensional Outline . . . . .	JEDEC No. TO-40
Case . . . . .	Metal and Plastic

Terminal Diagram:

Pin 1 - Emitter  
Pin 2 - Base



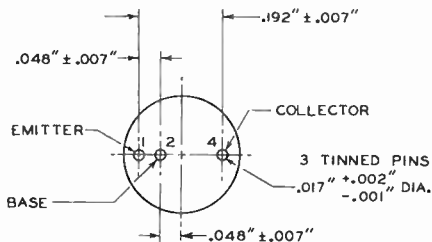
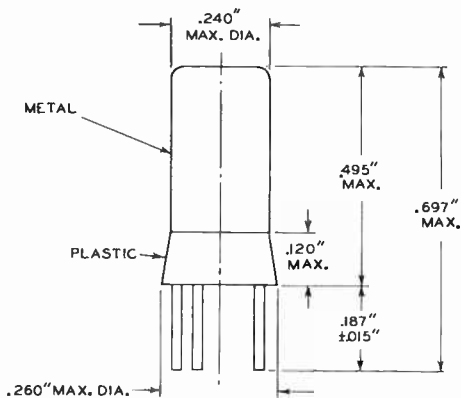
Pin 4 - Collector

### OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.



# 2N1527



PIN-SPACING TOLERANCES ARE NOT CUMULATIVE  
92CS-8550R7



## Transistor

### SILICON N-P-N DOUBLE-DIFFUSED-JUNCTION PLANAR TYPE

For Industrial and Military Applications

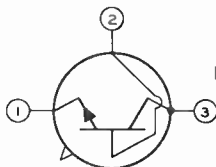
The 2N2102, having Higher Ratings, is  
a Direct Replacement for Type 2N1613

#### GENERAL DATA

##### Mechanical:

Operating Position. . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter. . . . .	0.370"
Dimensional Outline . . . . .	JEDEC No. TO-5
Case. . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length. . . . .	1.5"
Orientation and diameter. . . . .	See Dimensional Outline
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector,  
Case

#### INDUSTRIAL SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values:*

COLLECTOR-TO-BASE VOLTAGE:		
With emitter open. . . . .	75 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With external resistance (ohms) $\leq 10$ between base and emitter . . . . .	50 max.	volts
EMITTER-TO-BASE VOLTAGE:		
With collector open. . . . .	7 max.	volts
COLLECTOR CURRENT. . . . .		
	1 max.	amp
TRANSISTOR DISSIPATION: <sup>a</sup>		
At case temperature <sup>b</sup> of 25°C or below . . . . .	3 max.	watts
At free-air temperature of 25°C or below. . . . .	0.8 max.	watt
TEMPERATURE RANGE:		
Storage. . . . .	-65 to +300	°C
Operating (Junction) . . . . .	-65 to +200	°C
LEAD TEMPERATURE: <sup>c</sup>		
For 10 seconds maximum . . . . .	255 max.	°C

<sup>a</sup> See accompanying Rating Chart.

<sup>b</sup> Measured at center of seating plane.

<sup>c</sup> Measured 1/16"  $\pm$  1/32" down from seating plane.



# 2N1613

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and at case temperature<sup>b</sup> of 25° C unless otherwise specified

		Min.	Max.	
DC Collector Breakdown Voltage for dc collector ma. = 0.1, dc emitter ma. = 0. . . . .	$V_{CB0}$	75	-	volts
DC Emitter Breakdown Voltage for dc collector ma. = 0, dc emitter ma. = 0.25 . . . . .	$V_{EB0}$	7	-	volts
DC Collector-to-Emitter Reach-Through Voltage for dc emitter volts = 1.5, dc collector ma. = 0.1. . . . .	$V_{RT}$	75	-	volts
DC Collector-to-Emitter Sustaining Voltage for dc collector ma. = 100: With external base-to-emitter resistance (ohms) $\leq 10$ . . . . .	$V_{CE}(sus)$	50	-	volts
DC Base-to-Emitter Saturation Voltage for dc collector ma. = 150, dc base ma. = 15. . . . .	$V_{BE}(sat)$	-	1.3	volts
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = 150, dc base ma. = 15. . . . .	$V_{CE}(sat)$	-	1.5	volts
DC Collector-Cutoff Current for dc collector volts = 60, dc emitter ma. = 0, case temperature <sup>b</sup> =	$I_{CB0}$			
25° C . . . . .		-	0.01	$\mu a$
150° C . . . . .		-	10	$\mu a$
DC Emitter-Cutoff Current for dc base volts = 5, dc collector ma. = 0. . . . .	$I_{EB0}$	-	0.01	$\mu a$
Input Resistance at frequency of 1 kc:	$h_{ib}$			
with dc collector-to-emitter volts = 5, dc collector ma. = 1. . . . .		24	34	ohms
with dc collector-to-emitter volts = 10, dc collector ma. = 5. . . . .		4	8	ohms
Input Capacitance for dc emitter volts = 0.5, dc collector ma. = 10 . . . . .	$C_{ib}$	-	80	$\mu\mu f$
Output Capacitance for dc collector volts = 10, dc emitter ma. = 0. . . . .	$C_{ob}$	-	25	$\mu\mu f$



Output Conductance at frequency of 1 kc: With dc collector-to-emitter volts = 5, dc collector ma. = 1. . . . .	$h_{ob}$	0.1	0.5	$\mu\text{mho}$
With dc collector-to-emitter volts = 10, dc collector ma. = 5 . . . . .		0.1	1	$\mu\text{mho}$
Small-Signal Forward Current Transfer Ratio: With dc collector-to-emitter volts = 5, dc collector ma. = 1, frequency (kc) = 1. . . . .	$h_{fe}$	30	100	
With dc collector-to-emitter volts = 10, dc collector ma. = 5, frequency (kc) = 1. . . . .		35	150	
With dc collector-to-emitter volts = 10, dc collector ma. = 50, frequency (Mc) = 20 . . . . .		3	-	
DC-Pulse Forward-Current Transfer Ratio for dc collector-to-emitter volts = 10, pulse width ( $\mu\text{sec}$ ) = 300, duty factor of 0.018, dc collector ma. =	$h_{FE}$			
150. . . . .		40	120	
500. . . . .		20	-	
DC Forward Current Transfer Ratio: With dc collector-to-emitter volts = 10, dc collector ma. =	$h_{FE}$			
0.1. . . . .		20	-	
10 . . . . .		35	-	
With dc collector-to-emitter volts = 10, dc collector ma. = 10, case temperature <sup>b</sup> of -55° C . . . . .		20	-	
Voltage-Feedback Ratio at frequency of 1 kc: With dc collector-to-emitter volts = 5, dc collector ma. = 1. . . . .	$h_{rb}$	-	$3 \times 10^{-4}$	
With dc collector-to-emitter volts = 10, dc collector ma. = 5. . . . .		-	$3 \times 10^{-4}$	



# 2N1613

Noise Figure for signal frequency of 1 kc, circuit bandwidth of 15 kc, generator resistance (ohms) = 1000, dc collector-to-emitter volts = 10, dc collector ma. = 0.3. . . . .	NF	-	12	db
Total Switching Time <sup>d</sup> (Delay time + rise time + fall time). . . . .	$t_d+t_r+t_f$	-	30	$\mu\text{sec}$
Thermal Resistance:	$R_T$			
Junction-to-case. . . . .		-	58.3	$^{\circ}\text{C}/\text{watt}$
Junction-to-free air. . . . .		-	291.5	$^{\circ}\text{C}/\text{watt}$

<sup>b</sup> Measured at center of seating plane.

<sup>d</sup> See accompanying *Total-Switching-Time Measurement Circuit*.

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

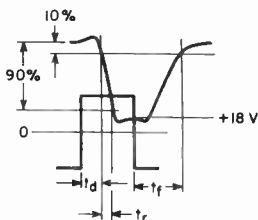
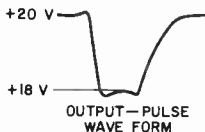
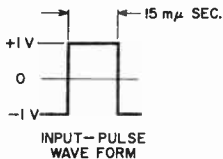
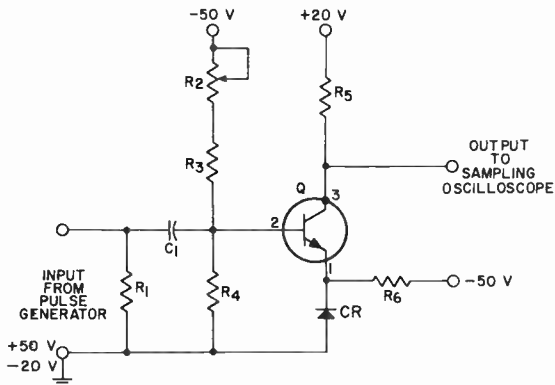
The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the seating plane provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.

This transistor is intended for socketed, single-side printed-circuit boards and in conventional wire-in type circuits. If this transistor is used in double-side printed-circuit boards or in printed-circuit boards utilizing eyelets, it may be necessary to use an insulating washer or similar standoff device made of good dielectric material to prevent the solder from shorting the leads to each other or to the board, and to prevent the collector from shorting to ground.

It is to be noted that the case of this transistor operates at the collector voltage. Consideration, therefore, should be given to the possibility of shock hazard, if the case of this transistor is to operate at a voltage appreciably above or below ground potential. In such cases, suitable precautionary measures should be taken.



## TOTAL-SWITCHING-TIME MEASUREMENT CIRCUIT AND ASSOCIATED WAVE FORMS



92CS-III86RI

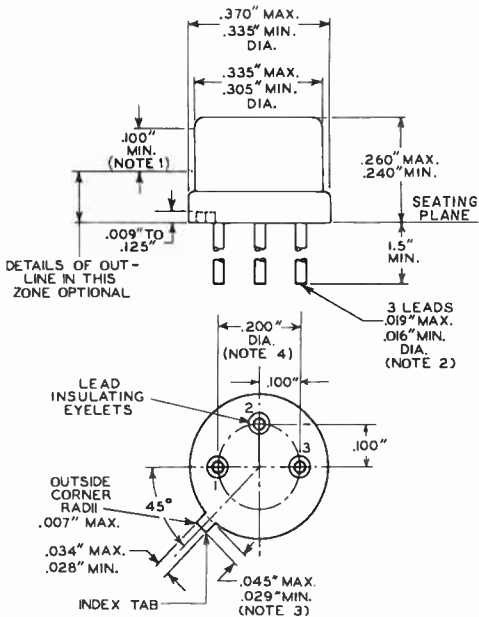
$C_1$ : 0.01  $\mu$ f  
 CR: Semiconductor diode  
       type 1N3064  
 Q: Transistor type 2N1613  
 $R_1$ : 100 ohms

$R_2$ : 1000 ohms  
 $R_3$ : 4700 ohms  
 $R_4$ : 100 ohms  
 $R_5$ : 40 ohms  
 $R_6$ : 1000 ohms, 5 watts



# 2N1613

JEDEC No. T0-5



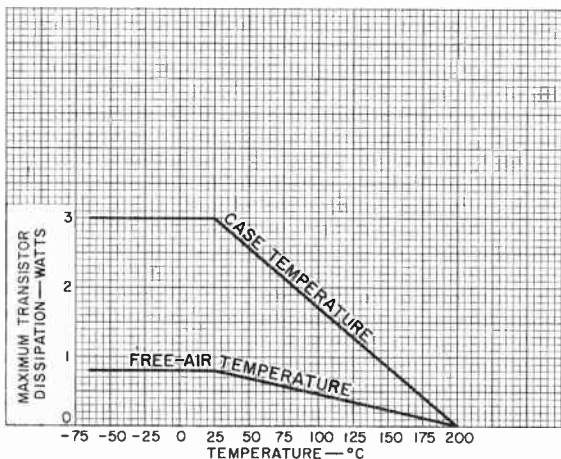
**NOTE 1:** THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE VARIATION IN ACTUAL DIAMETER WITHIN THE ZONE SHALL NOT EXCEED 0.010".

**NOTE 2:** THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE SEATING PLANE. BETWEEN 0.25" AND 1.5" A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

**NOTE 3:** MEASURED FROM MAXIMUM DIAMETER OF THE ACTUAL DEVICE.

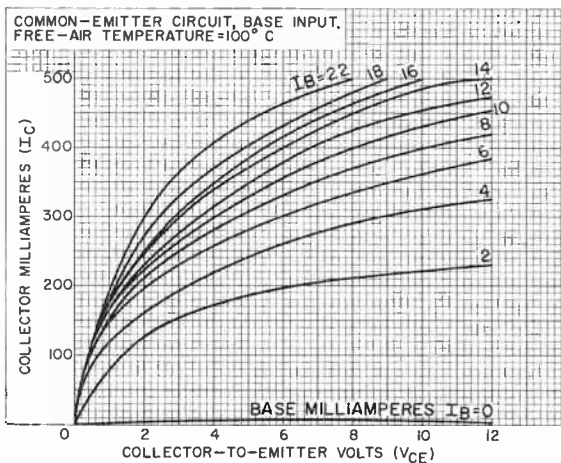
**NOTE 4:** LEADS HAVING MAXIMUM DIAMETER (0.019") MEASURED IN GAUGING PLANE 0.054" + 0.001" - 0.000" BELOW THE SEATING PLANE OF THE DEVICE SHALL BE WITHIN 0.007" OF THEIR TRUE LOCATIONS RELATIVE TO A MAXIMUM-WIDTH TAB.

## RATING CHART



92CS-III73RI

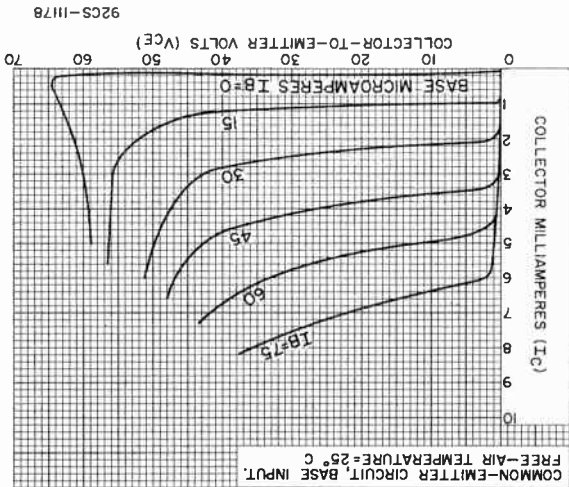
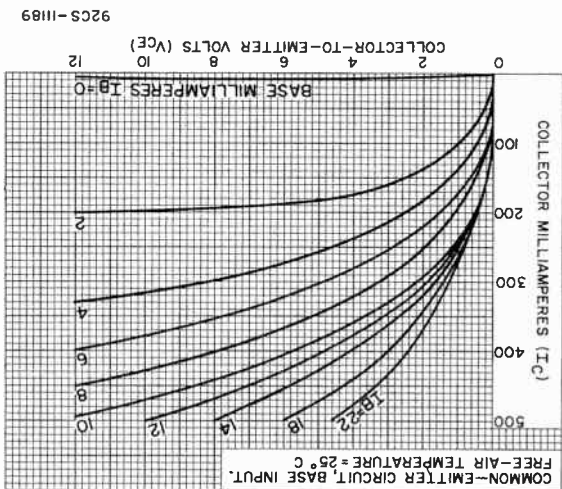
## TYPICAL COLLECTOR CHARACTERISTICS



92CS-III80

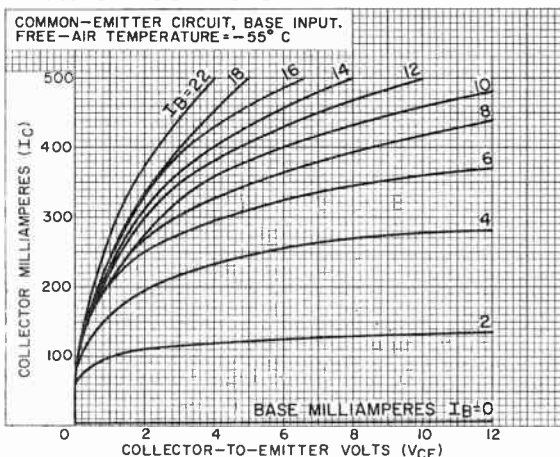


## TYPICAL COLLECTOR CHARACTERISTICS



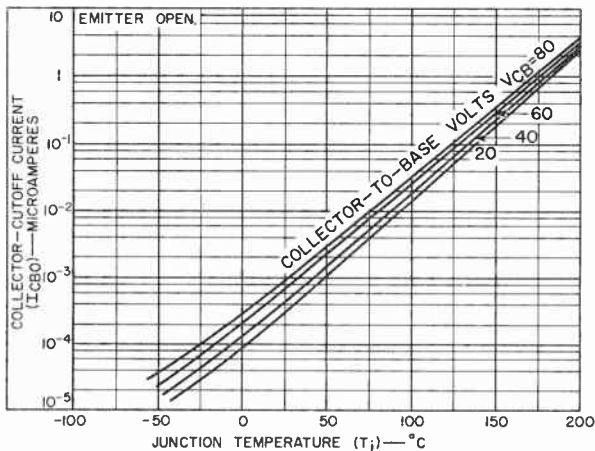


## TYPICAL COLLECTOR CHARACTERISTICS



92CS-1119I

## TYPICAL COLLECTOR-CUTOFF-CURRENT CHARACTERISTICS

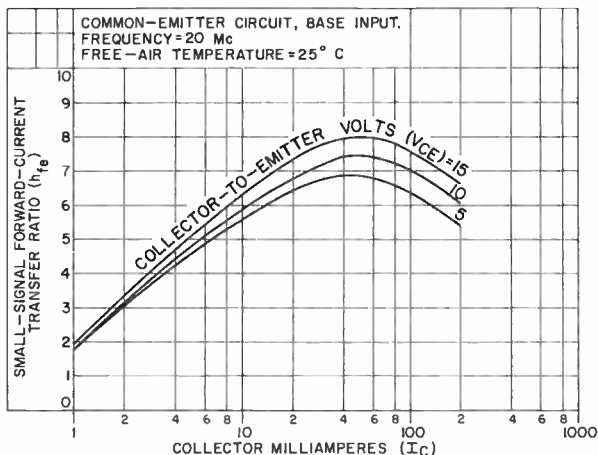


92CS-1117O

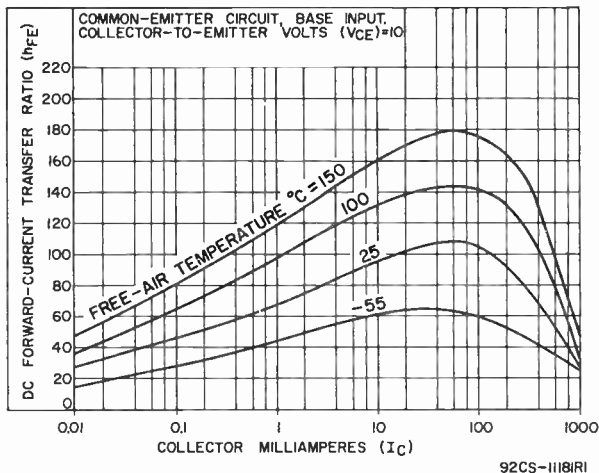


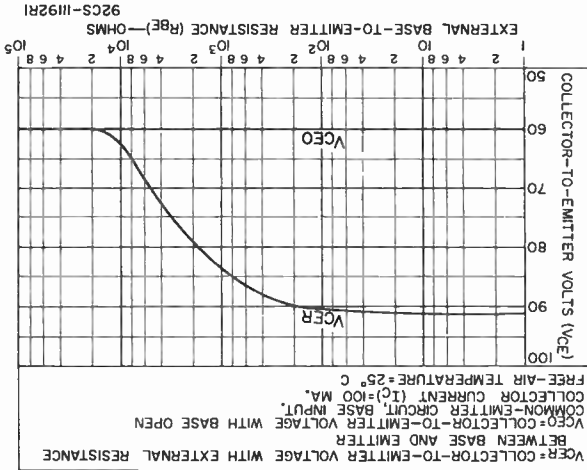
# 2N1613

## TYPICAL SMALL-SIGNAL FORWARD-CURRENT TRANSFER-RATIO CHARACTERISTICS



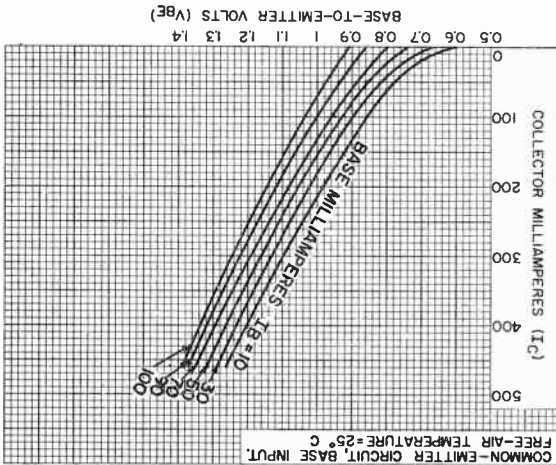
## TYPICAL DC FORWARD-CURRENT TRANSFER-RATIO CHARACTERISTICS





### TYPICAL COLLECTOR-TO-EMITTER VOLTAGE CHARACTERISTICS

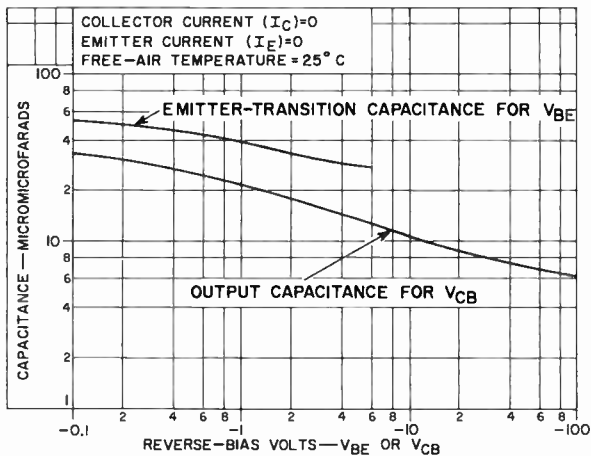
92CS-11185



### TYPICAL TRANSFER CHARACTERISTICS

2N1613

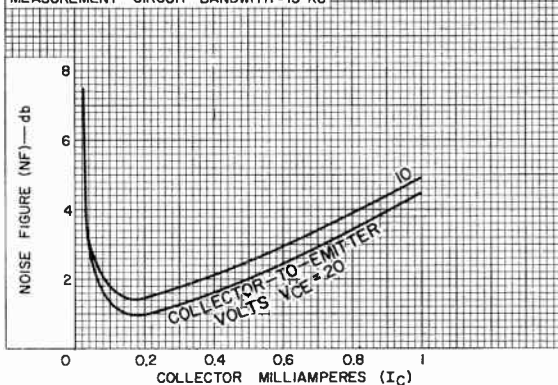
## TYPICAL EMITTER-TRANSITION-CAPACITANCE AND OUTPUT-CAPACITANCE CHARACTERISTICS



92CS-11195

## TYPICAL AF NOISE-FIGURE CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT.  
 FREE-AIR TEMPERATURE = 25° C  
 GENERATOR RESISTANCE = 1000 OHMS  
 SIGNAL FREQUENCY = 1 KC  
 MEASUREMENT-CIRCUIT BANDWIDTH = 15 KC



92CS-11179RI



## Drift-Field Transistor

## GERMANIUM P-N-P ALLOY TYPE

For Radio-Frequency-Amplifier Applications  
in Battery-Operated AM Radio Receivers

## GENERAL DATA

## Electrical:

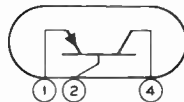
Minimum DC Collector-to-Base Breakdown Voltage ( $BV_{CB0}$ ) for dc collector $\mu a = -50$ , emitter open, ambient temperature = $25^{\circ} C$ . . . . .	-34	volts
Maximum DC Collector-Cutoff Current ( $I_{CB0}$ ) for dc collector-to-base volts = -12, emitter open, ambient temperature = $25^{\circ} C$ . . . . .	-16	$\mu a$
Maximum DC Emitter-Cutoff Current ( $I_{EB0}$ ) for dc emitter-to-base volts = -0.5, collector open, ambient temperature = $25^{\circ} C$ . . . . .	-16	$\mu a$
Maximum Junction-Temperature Rise (In free air) . . . . .	0.4	$^{\circ}C/mw$

## Mechanical:

Operating Position . . . . .	Any
Maximum Overall Length . . . . .	0.697"
Maximum Seated Length . . . . .	0.495"
Maximum Diameter . . . . .	0.260"
Dimensional Outline . . . . .	JEDEC No. T0-40
Case . . . . .	Metal and Plastic
Seals . . . . .	Hermetic

## Terminal Diagram:

Pin 1 - Emitter  
Pin 2 - Base



Pin 4 - Collector

## RADIO-FREQUENCY AMPLIFIER

## Maximum and Minimum Ratings, Absolute-Maximum Values:

DC COLLECTOR-TO-BASE VOLTAGE . . . . .	-34 max.	volts
DC EMITTER-TO-BASE VOLTAGE . . . . .	-0.5 max.	volt
DC COLLECTOR CURRENT . . . . .	-10 max.	ma
DC EMITTER CURRENT . . . . .	10 max.	ma
TRANSISTOR DISSIPATION:		
At ambient temperature of $25^{\circ} C$ . . . . .	80 max.	mw
At ambient temperature of $55^{\circ} C$ . . . . .	50 max.	mw
At ambient temperature of $71^{\circ} C$ . . . . .	35 max.	mw



# 2N1631

AMBIENT TEMPERATURE (During operation) . . . . . 71 max. °C  
 STORAGE-TEMPERATURE RANGE . . . . . -65 to +85 °C

## Characteristics, At Ambient Temperature of 25° C:

### Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage . . . . . -12 volts  
 DC Collector Current . . . . . 1 ma  
 Small-Signal Current Transfer  
 Ratio at 1 kc . . . . . 80

### Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage . . . . . -12 volts  
 DC Emitter Current . . . . . 1 ma  
 Small-Signal Current Transfer  
 Ratio at 1 kc . . . . . 0.987  
 Alpha-Cutoff Frequency . . . . . 45 Mc

## Typical Operation, At Ambient Temperature of 25° C:

### In a Common-Emitter Circuit, Base Input at a signal frequency of 1.5 Mc

DC Supply Voltage . . . . .	-6	-9	-12	volts
DC Collector-to-Emitter Voltage . . . . .	-5.7	-8.5	-11	volts
DC Emitter Current . . . . .	1	1	1	ma
Input Resistance, ac output circuit shorted . . . . .	520	750	1000	ohms
Output Resistance, ac input circuit shorted . . . . .	0.065	0.11	0.18	megohm
Extrinsic Transconductance . . . . .	36000	36000	36000	μmhos
Collector-to-Base Capacitance (C <sub>ob</sub> ) . . . . .	2.2 <sup>▲</sup>	2.1 <sup>▲</sup>	2 <sup>▲</sup>	μμf
Maximum Power Gain* . . . . .	40.4	44.3	47.7	db
Useful Power Gain:				
In unneutralized circuit. . . . .	25.3	25.5	25.6	db

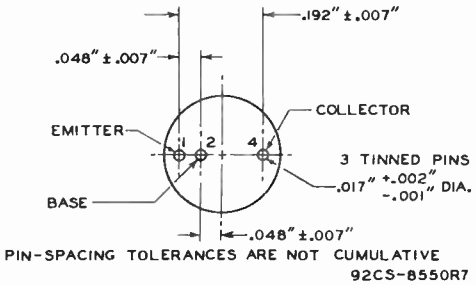
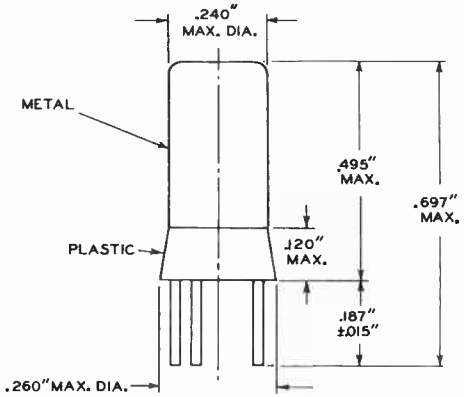
<sup>▲</sup> Maximum variation from this value is 0.9 μμf.

\* Measured in a single-tuned unilateralized circuit matched to the generator and load impedance for maximum transfer of power (transformer-insertion losses not included).

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

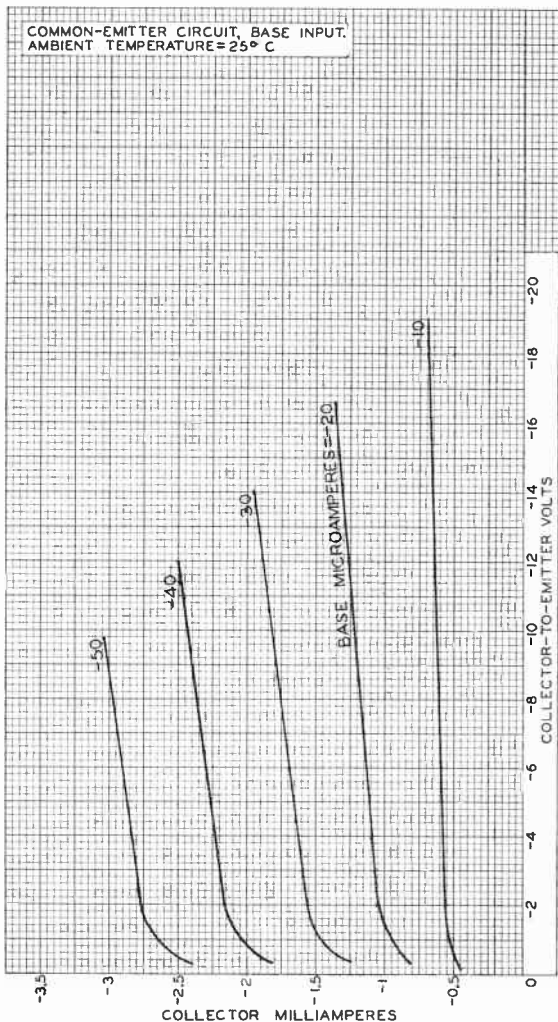




# 2N1631

## TYPICAL COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT.  
AMBIENT TEMPERATURE = 25° C

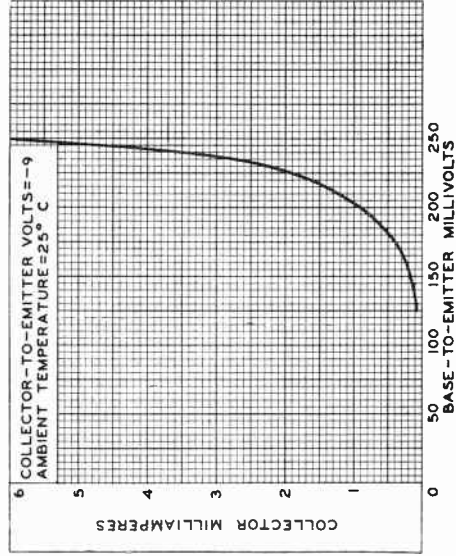
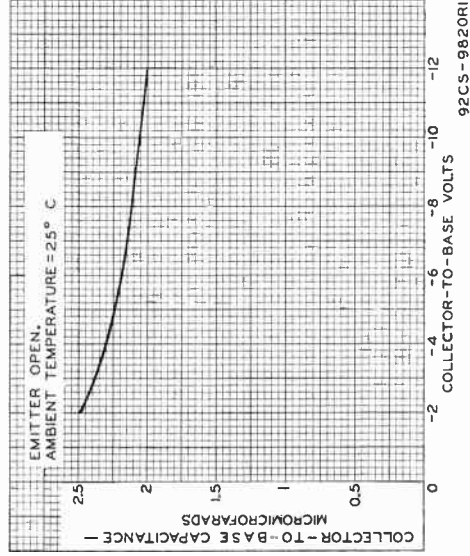


92CM-9107

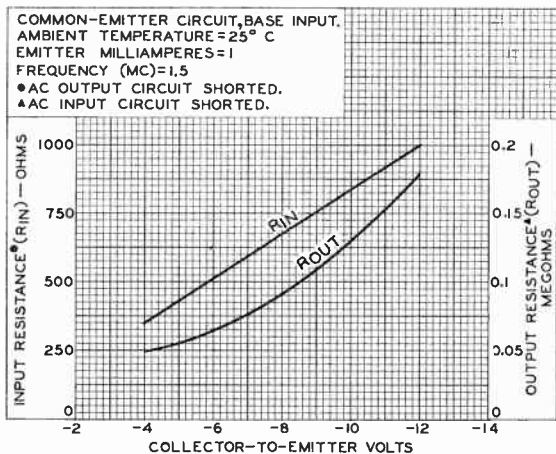




## TYPICAL CHARACTERISTICS



## TYPICAL CHARACTERISTICS



92CS-10561RI

## Drift-Field Transistor

## GERMANIUM P-N-P ALLOY TYPE

For Radio-Frequency-Amplifier Applications in Battery-Operated Radio Receivers

The 2N1632 is the same as the 2N1631 except for the following items:

**Mechanical:**

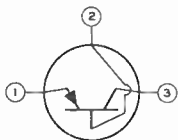
Maximum Length (Excluding flexible leads) . . . . .	0.410"
Maximum Diameter . . . . .	0.260"
Dimensional Outline . . . . .	JEDEC No. TO-1
Case . . . . .	Metal
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See Dimensional Outline

Terminal Diagram:

BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base



Lead 3 - Collector  
(Adjacent to red dot on side of case)

**OPERATING CONSIDERATIONS**

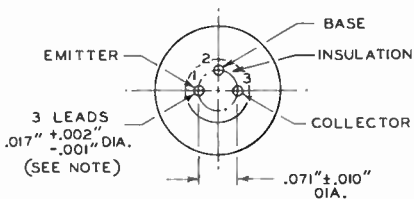
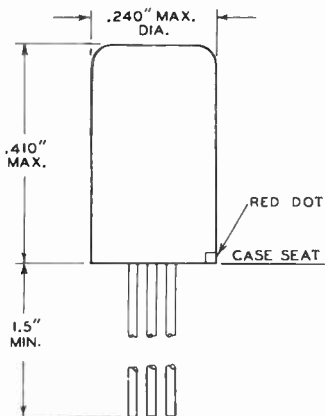
It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The flexible leads of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using this transistor, the temperature of the solder should not exceed 255° C for a maximum immersion period of 10 seconds.



# 2N1632



92CS-9148R6

NOTE: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN  $0.05''$  AND  $0.25''$  FROM THE CASE SEAT. BETWEEN  $0.25''$  AND  $1.5''$ , A MAXIMUM DIAMETER OF  $0.021''$  IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

## Drift-Field Transistor

## GERMANIUM P-N-P ALLOY TYPE

For Intermediate-Frequency-Amplifier Applications  
in Battery-Operated AM Radio Receivers

## GENERAL DATA

## Electrical:

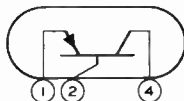
Minimum DC Collector-to-Base Breakdown Voltage ( $BV_{CBO}$ ) for dc collector $\mu a = -50$ , emitter open, ambient temperature = $25^{\circ} C$ .	-34	volts
Maximum DC Collector-Cutoff Current ( $I_{CBO}$ ) for dc collector-to-base volts = -12, emitter open, ambient temperature = $25^{\circ} C$ .	-16	$\mu a$
Maximum DC Emitter-Cutoff Current ( $I_{EBO}$ ) for dc emitter-to-base volts = -0.5, collector open, ambient temperature = $25^{\circ} C$ .	-16	$\mu a$
Maximum Junction-Temperature Rise (In free air).	0.4	$^{\circ}C/mw$

## Mechanical:

Operating Position	Any
Maximum Overall Length	0.697"
Maximum Seated Length	0.495"
Maximum Diameter	0.260"
Dimensional Outline	JEDEC No. TO-40
Case	Metal and Plastic
Seals	Hermetic

## Terminal Diagram:

Pin 1 - Emitter  
Pin 2 - Base



Pin 4 - Collector

## INTERMEDIATE-FREQUENCY AMPLIFIER

## Maximum and Minimum Ratings, Absolute-Maximum Values:

DC COLLECTOR-TO-BASE VOLTAGE	-34 max.	volts
DC EMITTER-TO-BASE VOLTAGE	-0.5 max.	volt
DC COLLECTOR CURRENT	-10 max.	ma
DC EMITTER CURRENT	10 max.	ma
TRANSISTOR DISSIPATION:		
At ambient temperature of $25^{\circ} C$ .	80 max.	mw
At ambient temperature of $55^{\circ} C$ .	50 max.	mw
At ambient temperature of $71^{\circ} C$ .	35 max.	mw
AMBIENT TEMPERATURE (During operation)	71 max.	$^{\circ}C$
STORAGE-TEMPERATURE RANGE.	-65 to +85	$^{\circ}C$



# 2N1633

## Characteristics, At Ambient Temperature of 25° C:

### Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage. . . . .	-12	volts
DC Emitter Current . . . . .	1	ma
Small-Signal Current Transfer Ratio at 1 kc. . . . .	75	

### Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage . . . . .	-12	volts
DC Emitter Current . . . . .	1	ma
Small-Signal Current Transfer Ratio at 1 kc. . . . .	0.986	
Alpha-Cutoff Frequency . . . . .	40	Mc

## Typical Operation, At Ambient Temperature of 25° C:

*In a common-emitter, base-input, single-stage, 455-kc intermediate-frequency-amplifier circuit*

DC Supply Voltage. . . . .	-6	-9	-12	volts
DC Collector-to-Emitter Voltage. . . . .	-5.7	-8.5	-11	volts
DC Emitter Current . . . . .	1	1	1	ma
Input Resistance, ac output circuit shorted. . . . .	1500	1550	1800	ohms
Output Resistance, ac input circuit shorted. . . . .	0.35	0.475	0.6	megohm
Collector-to-Base Capacitance (C <sub>Ob</sub> ). . . . .	2.2 <sup>▲</sup>	2.1 <sup>▲</sup>	2 <sup>▲</sup>	μμf
Maximum Power Gain*. . . . .	52.6	53.8	55.7	db
Maximum Useful Power Gain:				
In neutralized circuit . . . . .	36.7	36.7	36.7	db
In unneutralized circuit . . . . .	31.2	31.3	31.4	db

*In a common-emitter, base-input, two-stage, 455-kc intermediate-frequency-amplifier circuit*

DC Supply Voltage. . . . .	-6	-6	-9	-9	-12	-12	volts
DC Collector- to-Emitter Voltage. . . . .	-5.7	-5.7	-8.5	-8.5	-11	-11	volts
DC Emitter Current. . . . .	0.5	1	0.5	1	0.5	1	ma
Input Resist- ance, ac out- put circuit shorted. . . . .	2800	1500	3000	1550	3400	1800	ohms
Output Resist- ance, ac in- put circuit shorted. . . . .	0.7	0.35	0.9	0.475	1.2	0.6	megohms
Collector-to- Base Capac- itance (C <sub>Ob</sub> ) . . . . .	2.2 <sup>▲</sup>	2.2 <sup>▲</sup>	2.1 <sup>▲</sup>	2.1 <sup>▲</sup>	2 <sup>▲</sup>	2 <sup>▲</sup>	μμf
Maximum Power Gain*. . . . .	52.2	52.6	53.3	53.8	55.6	55.7	db



## Useful Power

Gain:

In neu- tralized circuit. . .	32.4	35.2	32.4	35.2	32.4	35.2	db
In unneu- tralized circuit. . .	27.7	29.7	27.9	29.8	28	29.9	db

▲ Maximum variation from this value is 0.9  $\mu\mu\text{f}$ .

● Measured in a single-tuned unilateralized circuit matched to the generator and load impedance for maximum transfer of power (transformer-insertion losses not included).

OPERATING CONSIDERATIONS  
and DIMENSIONAL OUTLINE

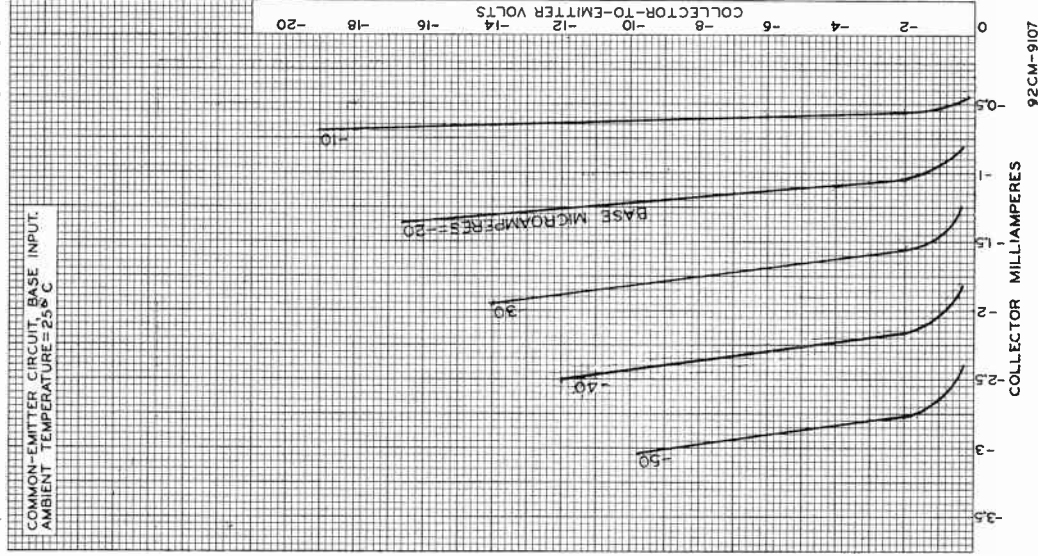
shown under type 2N1631 also apply to the 2N1633



# 2N1633

## TYPICAL COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT.  
AMBIENT TEMPERATURE = 25°C



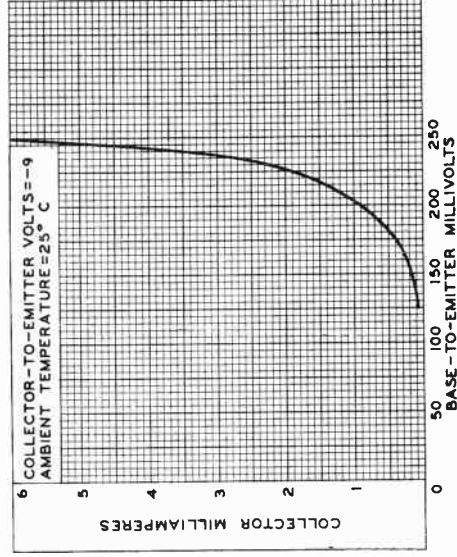
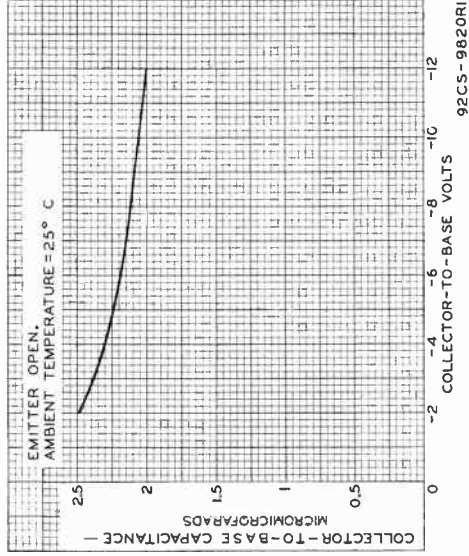
92CM-9107



RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division  
Somerville, N. J.



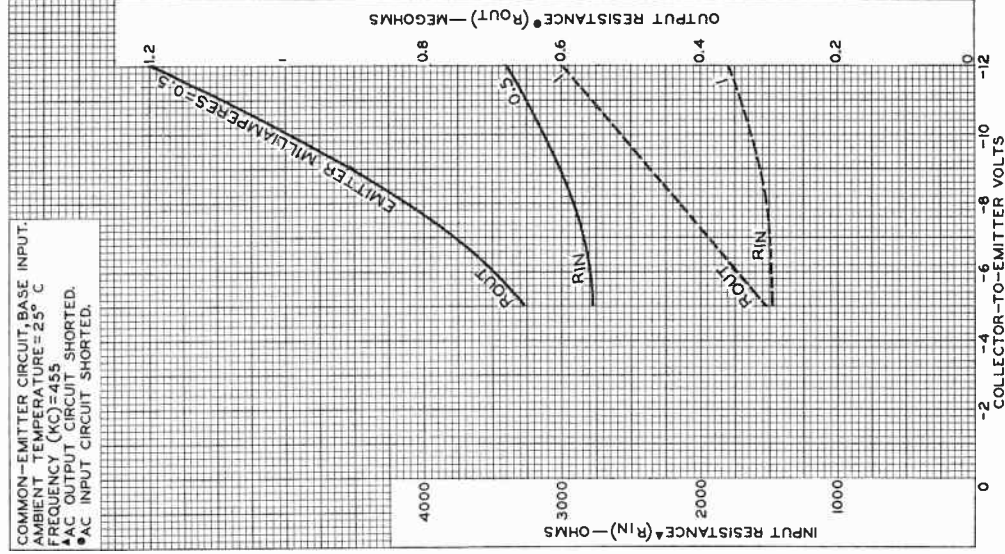
## TYPICAL CHARACTERISTICS



# 2N1633

## TYPICAL CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT.  
AMBIENT TEMPERATURE = 25° C  
FREQUENCY (KC) = 455  
▲ AC OUTPUT CIRCUIT SHORTED.  
● AC INPUT CIRCUIT SHORTED.



92CM-10562RI

## Drift-Field Transistor

## GERMANIUM P-N-P ALLOY TYPE

For Intermediate-Frequency-Amplifier Applications in Battery-Operated Radio Receivers

The 2N1634 is the same as the 2N1633 except for the following items:

## Mechanical:

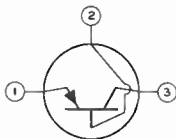
Maximum Length (Excluding flexible leads) . . . . . 0.410"  
 Maximum Diameter . . . . . 0.260"  
 Dimensional Outline . . . . . JEDEC No. TO-1  
 Case . . . . . Metal  
 Leads, Flexible . . . . . 3  
 Minimum length . . . . . 1.5"  
 Orientation and diameter . . . . . See Dimensional Outline

Terminal Diagram:

BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base



Lead 3 - Collector  
 (Adjacent to red dot on side of case)

## OPERATING CONSIDERATIONS

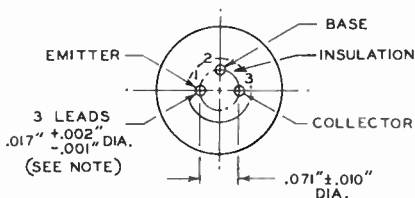
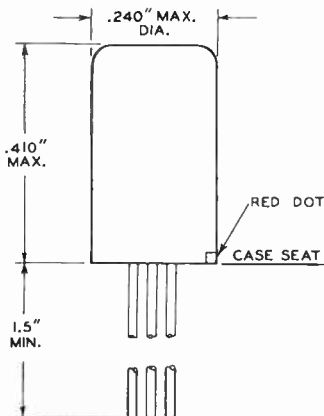
It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The flexible leads of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using this transistor, the temperature of the solder should not exceed 255° C for a maximum immersion period of 10 seconds.



# 2N1634



92CS-9148R6

NOTE: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE CASE SEAT. BETWEEN 0.25" AND 1.5", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

## Drift-Field Transistor

GERMANIUM P-N-P ALLOY TYPE

For Converter Applications in  
Battery-Operated AM Radio Receivers

### GENERAL DATA

#### Electrical:

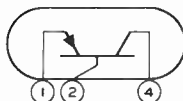
Minimum DC Collector-to-Base Breakdown Voltage ( $BV_{CBO}$ ) for dc collector $\mu a = -50$ , emitter open, ambient temperature = $25^{\circ} C$ . . . . .	-34	volts
Maximum DC Collector-Cutoff Current ( $I_{CBO}$ ) for dc collector-to-base volts = -12, emitter open, ambient temperature = $25^{\circ} C$ . . . . .	-16	$\mu a$
Maximum DC Emitter-Cutoff Current ( $I_{EBO}$ ) for dc emitter-to-base volts = -0.5, collector open, ambient temperature = $25^{\circ} C$ . . . . .	-16	$\mu a$
Maximum Junction-Temperature Rise (In free air) . . . . .	0.4	$^{\circ}C/mw$

#### Mechanical:

Operating Position . . . . .	Any
Maximum Overall Length . . . . .	0.697"
Maximum Seated Length . . . . .	0.495"
Maximum Diameter . . . . .	0.260"
Dimensional Outline . . . . .	JEDEC No. TO-40
Case . . . . .	Metal and Plastic
Seals . . . . .	Hermetic

#### Terminal Diagram:

Pin 1 - Emitter  
Pin 2 - Base



Pin 4 - Collector

### CONVERTER

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

DC COLLECTOR-TO-BASE VOLTAGE . . . . .	-34 max.	volts
DC EMITTER-TO-BASE VOLTAGE . . . . .	-0.5 max.	volt
DC COLLECTOR CURRENT . . . . .	-10 max.	ma
DC EMITTER CURRENT . . . . .	10 max.	ma
TRANSISTOR DISSIPATION:		
At ambient temperature of $25^{\circ} C$ . . . . .	80 max.	mw
At ambient temperature of $55^{\circ} C$ . . . . .	50 max.	mw
At ambient temperature of $71^{\circ} C$ . . . . .	35 max.	mw



# 2N1635

AMBIENT TEMPERATURE (During operation) . . . 71 max. °C  
STORAGE-TEMPERATURE RANGE . . . . . -65 to +85 °C

## Characteristics, At Ambient Temperature of 25° C:

### Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage . . . . . -12 volts  
DC Emitter Current . . . . . 1 ma  
Small-Signal Current Transfer  
Ratio at 1 kc . . . . . 75

### Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage . . . . . -12 volts  
DC Emitter Current . . . . . 1 ma  
Small-Signal Current Transfer  
Ratio at 1 kc . . . . . 0.986  
Alpha-Cutoff Frequency . . . . . 45 Mc

## Typical Operation, At Ambient Temperature of 25° C:

### In a common-emitter, base-input, self-excited, 1-Mc converter circuit

DC Supply Voltage . . . . . -9 volts  
DC Collector-to-Emitter Voltage . . . . . -8.5 volts  
DC Emitter Current . . . . . 0.65 ma  
Input Resistance . . . . . 2000 ohms  
Output Resistance . . . . . 0.3 megohm  
RMS Base-to-Emitter  
Oscillator-Injection Voltage . . . . . 100 mv  
Conversion Power Gain . . . . . 36 db

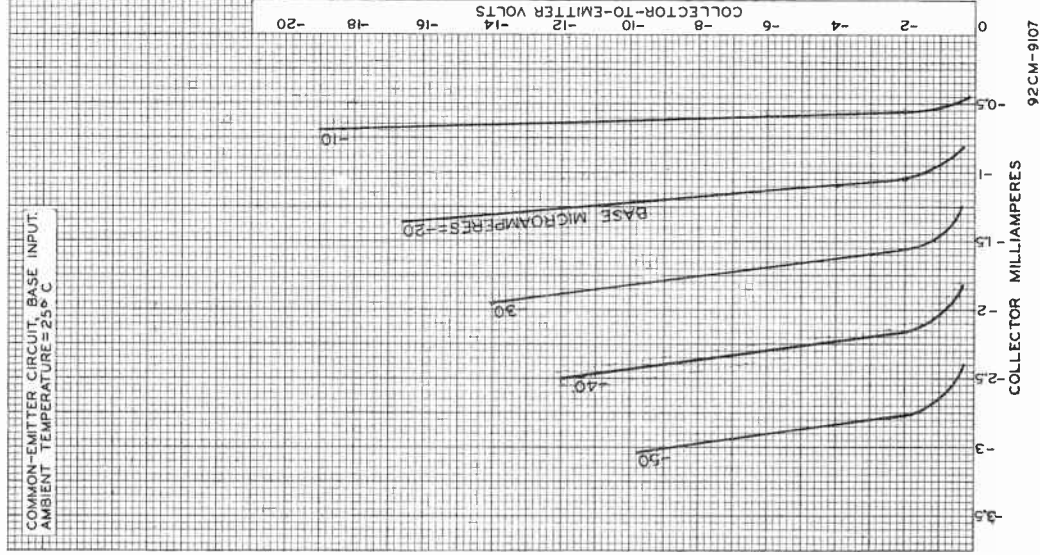
## OPERATING CONSIDERATIONS and DIMENSIONAL OUTLINE

shown under Type 2N1631 also apply to the 2N1635

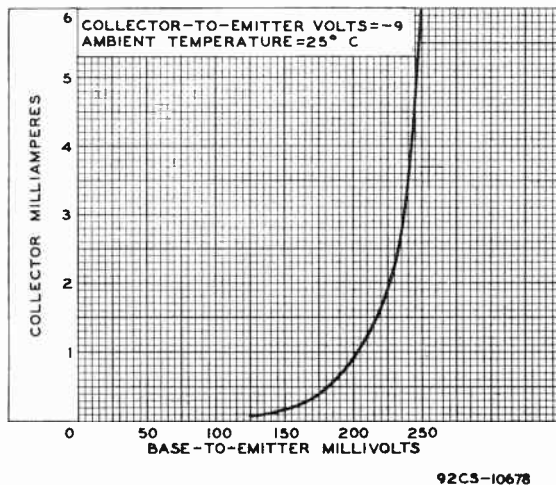
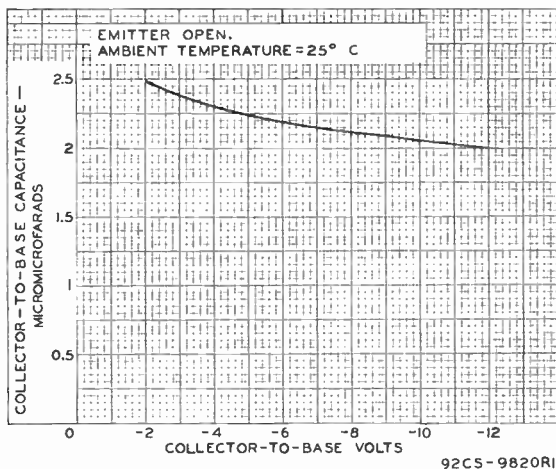


## TYPICAL COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT.  
 AMBIENT TEMPERATURE = 25° C

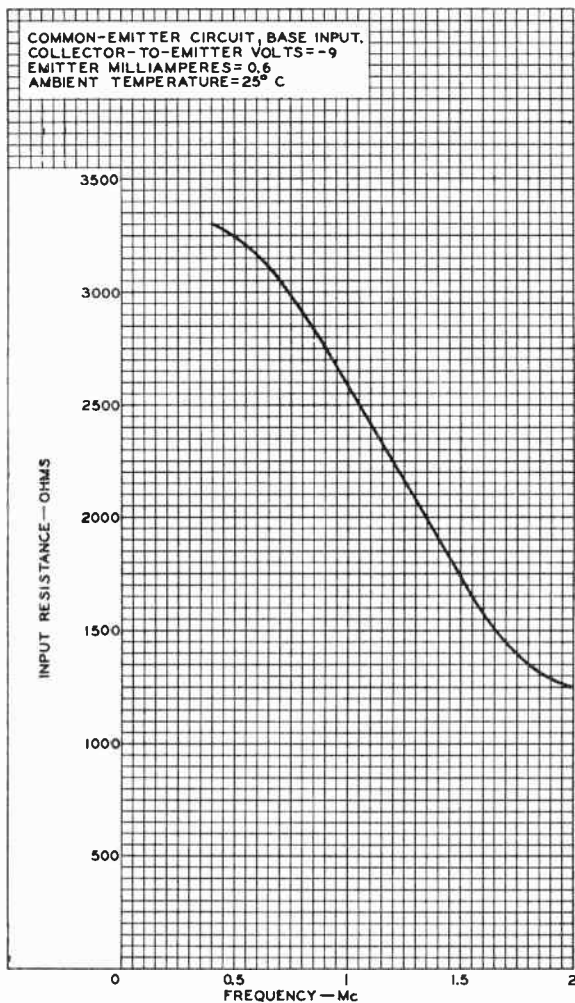


## TYPICAL CHARACTERISTICS





## TYPICAL CHARACTERISTIC



92CM-10682





## Drift-Field Transistor

## GERMANIUM P-N-P ALLOY TYPE

For Converter Application in  
Battery-Operated AM Radio Receivers

The 2N1636 is the same as the 2N1635 except for the following items:

## Mechanical:

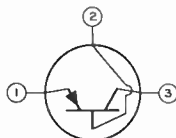
Maximum Length (Excluding flexible leads) . . . . .	0.410"
Maximum Diameter . . . . .	0.260"
Dimensional Outline . . . . .	JEDEC No. TO-1
Case . . . . .	Metal
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See Dimensional Outline

Terminal Diagram:

BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base



Lead 3 - Collector  
(Adjacent to red dot on side of case)

## OPERATING CONSIDERATIONS

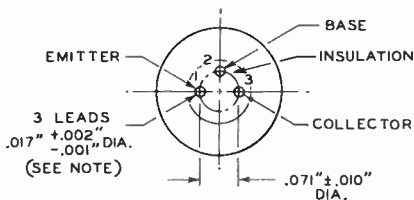
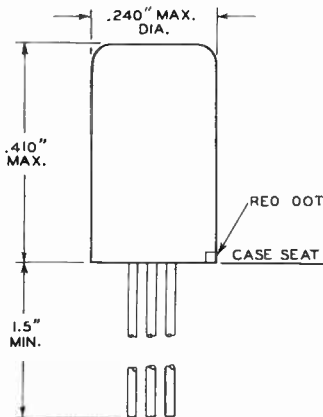
It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The flexible leads of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using this transistor, the temperature of the solder should not exceed 255° C for a maximum immersion period of 10 seconds.



# 2N1636



92CS-9148R6

NOTE: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE CASE SEAT. BETWEEN 0.25" AND 1.5", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

## Drift-Field Transistor

GERMANIUM P-N-P ALLOY TYPE

For Radio-Frequency-Amplifier Applications in AM Automobile-Radio Receivers

## GENERAL DATA

## Electrical:

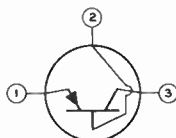
Minimum DC Collector-to-Base Breakdown Voltage ( $BV_{CBO}$ ) for dc collector $\mu$ = -50, emitter open, ambient temperature of 25° C. . . . .	-34	volts
Maximum DC Collector-Cutoff Current ( $I_{CBO}$ ) for dc collector-to-base volts = -12, emitter open, ambient temperature of 25° C. . . . .	-5	$\mu$ a
Maximum DC Emitter-Cutoff Current ( $I_{EBO}$ ) for dc emitter-to-base volts = -1.5, collector open, ambient temperature of 25° C. . . . .	-15	$\mu$ a
Maximum Junction-Temperature Rise (In free air). . . . .	0.4	°C/mw

## Mechanical:

Operating Position. . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.410"
Maximum Diameter. . . . .	0.240"
Dimensional Outline . . . . .	JEDEC No. TO-1
Case. . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length. . . . .	1.5"
Orientation and diameter. . . . .	See Dimensional Outline
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base

Lead 3 - Collector  
(Adjacent to red dot on side of case)

## RADIO-FREQUENCY AMPLIFIER

Maximum and Minimum Ratings, *Absolute-Maximum Values:*

DC COLLECTOR-TO-BASE VOLTAGE. . . . .	-34 max.	volts
DC EMITTER-TO-BASE VOLTAGE. . . . .	-1.5 max.	volts
DC COLLECTOR CURRENT. . . . .	-10 max.	ma
DC EMITTER CURRENT. . . . .	10 max.	ma



# 2N1637

## TRANSISTOR DISSIPATION:

At ambient temperature of 25° C. . . . .	80 max.	mw
At ambient temperature of 55° C. . . . .	50 max.	mw
At ambient temperature of 71° C. . . . .	35 max.	mw
AMBIENT TEMPERATURE (During operation) . .	71 max.	°C
STORAGE-TEMPERATURE RANGE. . . . .	-65 to +85	°C

## Characteristics, At Ambient Temperature of 25° C:

### Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage. . . . .	-12	volts
DC Collector Current . . . . .	-1	ma
Collector-to-Base Capacitance ( $C_{ob}$ ). . . . .	2 <sup>A</sup>	$\mu$ f
Small-Signal Current Transfer Ratio at 1 kc. . . . .	80	

### Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage . . . . .	-12	volts
DC Collector Current . . . . .	-1	ma
Small-Signal Current Transfer Ratio at 1 kc. . . . .	0.987	
Alpha-Cutoff Frequency . . . . .	45	Mc

## Typical Operation, At Ambient Temperature of 25° C:

### In a common-emitter circuit, base input at a signal frequency of 1.5 Mc

DC Collector-to-Emitter Voltage. . . . .	-5.5	-11.2	volts
DC Emitter Current . . . . .	1	1	ma
Input Resistance, ac output circuit shorted. . . . .	520	1000	ohms
Output Resistance, ac input circuit shorted. . . . .	0.065	0.18	megohm
Maximum Power Gain . . . . .	40.4	47.7	db
Maximum Useful Power Gain: In unneutralized circuit . . . . .	25.3	25.6	db

<sup>A</sup> Maximum variation from this value is 0.9  $\mu$ f.

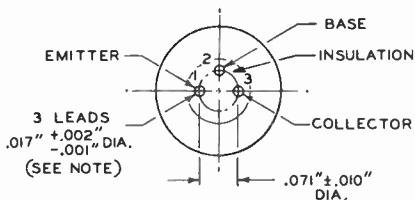
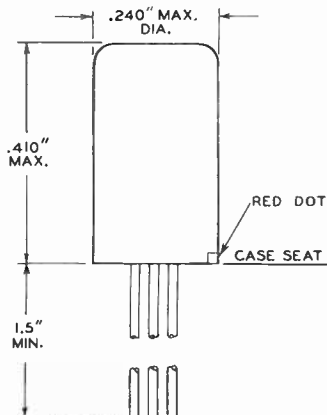
## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using this transistor, the temperature of the solder should not exceed 255° C for a maximum immersion period of 10 seconds.





92CS-9148R6

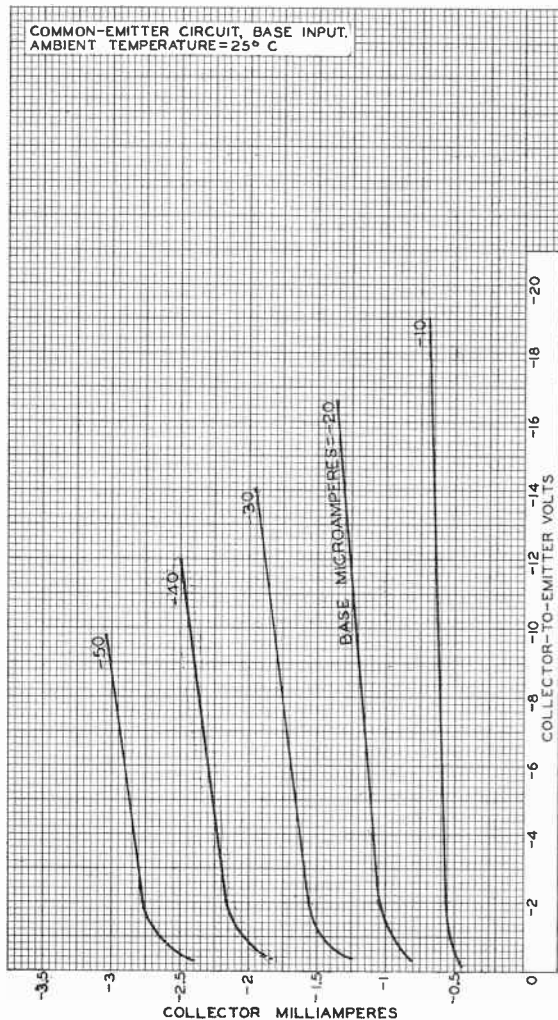
NOTE: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE CASE SEAT. BETWEEN 0.25" AND 1.5", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.



# 2N1637

## AVERAGE COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT.  
AMBIENT TEMPERATURE = 25° C



92CM-9107

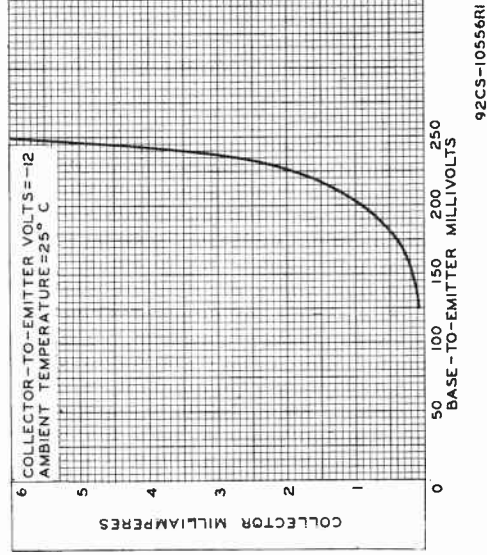
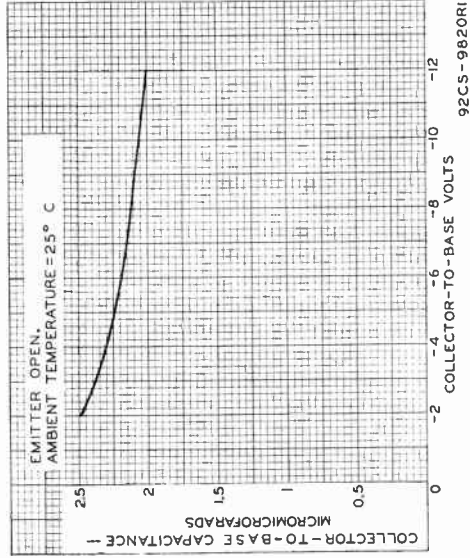
RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division  
Somerville, N. J.

World Radio History

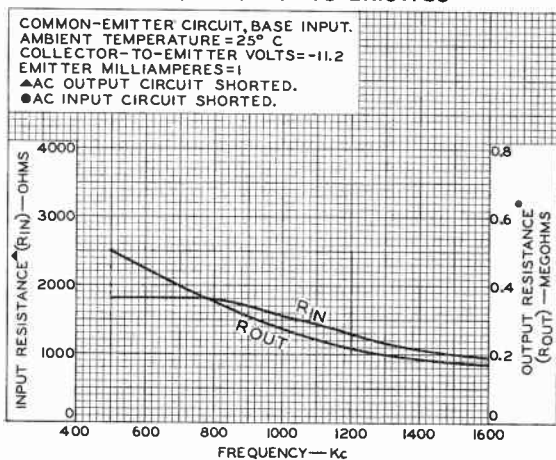




## TYPICAL CHARACTERISTICS



## TYPICAL CHARACTERISTICS



92CS-10587RI

## Drift-Field Transistor

GERMANIUM P-N-P ALLOY TYPE

For Intermediate-Frequency-Amplifier Applications in AM Automobile-Radio Receivers

### GENERAL DATA

#### Electrical:

Minimum DC Collector-to-Base Breakdown Voltage ( $BV_{CBO}$ ) for dc collector $\mu a = -50$ , emitter open, ambient temperature = $25^{\circ} C$ . . . . .	-34	volts
Maximum DC Collector-Cutoff Current ( $I_{CBO}$ ) for dc collector-to-base volts = -12, emitter open, ambient temperature = $25^{\circ} C$ . . . . .	-7	$\mu a$
Maximum DC Emitter-Cutoff Current ( $I_{EBO}$ ) for dc emitter-to-base volts = -0.5, collector open, ambient temperature = $25^{\circ} C$ . . . . .	-8	$\mu a$
Maximum Junction-Temperature Rise (In free air). . . . .	0.4	$^{\circ}C/mw$

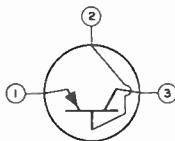
#### Mechanical:

Operating Position. . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.410"
Maximum Diameter. . . . .	0.240"
Dimensional Outline . . . . .	JEDEC No. TO-1
Case. . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length. . . . .	1.5"
Orientation and diameter. . . . .	See <i>Dimensional Outline</i>

#### Terminal Diagram: BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base



Lead 3 - Collector (Adjacent to red dot on side of case)

### INTERMEDIATE-FREQUENCY AMPLIFIER

Maximum and Minimum Ratings, Absolute-Maximum Values:

DC COLLECTOR-TO-BASE VOLTAGE. . . . .	-34 max.	volts
DC EMITTER-TO-BASE VOLTAGE. . . . .	-0.5 max.	volt
DC COLLECTOR CURRENT. . . . .	-10 max.	ma
DC EMITTER CURRENT. . . . .	10 max.	ma



# 2N1638

## TRANSISTOR DISSIPATION:

At ambient temperature of 25° C. . . . .	80 max.	mw
At ambient temperature of 55° C. . . . .	50 max.	mw
At ambient temperature of 71° C. . . . .	35 max.	mw
AMBIENT TEMPERATURE (During operation) . . . . .	71 max.	°C
STORAGE-TEMPERATURE RANGE. . . . .	- 65 to +85	°C

## Characteristics, At Ambient Temperature of 25° C:

### Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage. . . . .	-12	volts
DC Collector Current . . . . .	-1 <sup>▲</sup>	ma
Collector-to-Base Capacitance (C <sub>ob</sub> ). . . . .	2	μf
Small-Signal Current Transfer Ratio at 1 kc. . . . .	75	

### Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage . . . . .	-12	volts
DC Collector Current . . . . .	-1	ma
Small-Signal Current Transfer Ratio at 1 kc. . . . .	0.986	
Alpha-Cutoff Frequency . . . . .	40	Mc

## Typical Operation, At Ambient Temperature of 25° C:

*In a common-emitter, base-input, single-stage, 262.5-kc intermediate-frequency-amplifier circuit*

DC Collector-to-Emitter Voltage . . . . .	-5	-11	volts
DC Emitter Current . . . . .	1.6	2	ma
Input Resistance . . . . .	1800	1400	ohms
Output Resistance . . . . .	0.47	0.72	megohm
Maximum Power Gain . . . . .	58.6	61.5	db
Useful Power Gain:			
In unneutralized circuit . . . . .	35	36.6	db

<sup>▲</sup> Maximum variation from this value is 0.9 μμf.

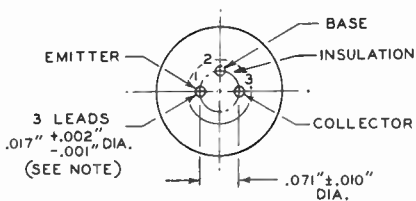
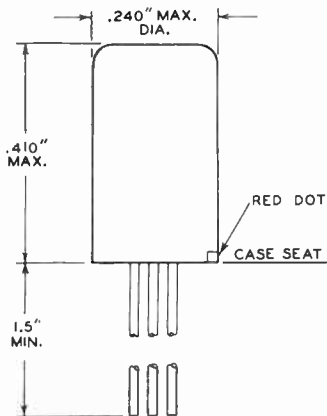
## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using this transistor, the temperature of the solder should not exceed 255° C for a maximum immersion period of 10 seconds.





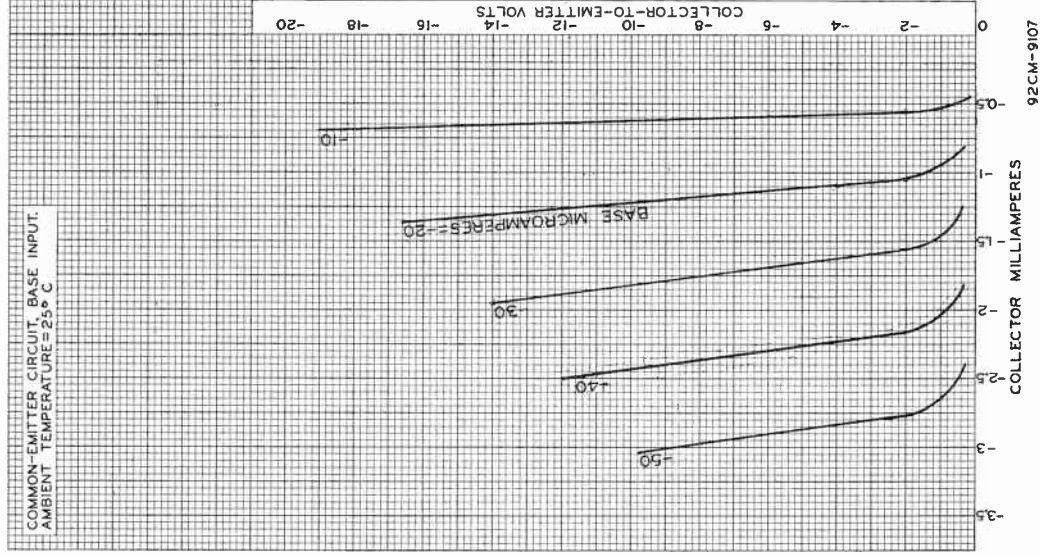
92CS-9148R6

NOTE: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE CASE SEAT. BETWEEN 0.25" AND 1.5", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.



# 2N1638

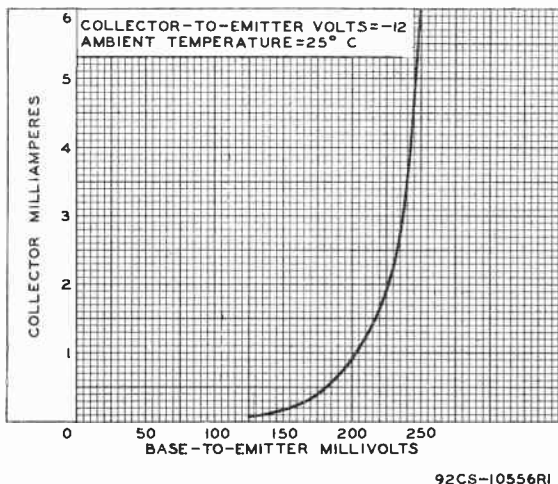
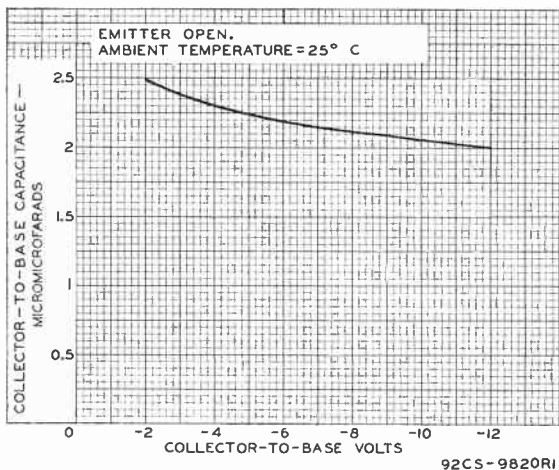
## AVERAGE COLLECTOR CHARACTERISTICS



World Precision



## TYPICAL CHARACTERISTICS







## Drift-Field Transistor

GERMANIUM P-N-P ALLOY TYPE  
For Converter Applications in  
AM Automobile-Radio Receivers

## GENERAL DATA

## Electrical:

Minimum DC Collector-to-Base Breakdown Voltage ( $BV_{CBO}$ ) for dc collector $\mu a = -50$ , emitter open, ambient temperature = $25^{\circ} C$ .	-34	volts
Maximum DC Collector-Cutoff Current ( $I_{CBO}$ ) for dc collector-to-base volts = -12, emitter open, ambient temperature = $25^{\circ} C$ .	-7	$\mu a$
Maximum DC Emitter-Cutoff Current ( $I_{EBO}$ ) for dc emitter-to-base volts = -0.5, collector open, ambient temperature = $25^{\circ} C$ .	-8	$\mu a$
Maximum Junction-Temperature Rise (In free air)	0.4	$^{\circ}C/mw$

## Mechanical:

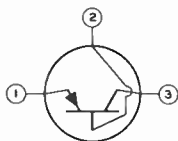
Operating Position	. . . . .	Any
Maximum Length (Excluding flexible leads)	. . . . .	0.410"
Maximum Diameter	. . . . .	0.240"
Dimensional Outline	. . . . .	JEDEC No. TO-1
Case	. . . . .	Metal
Seals	. . . . .	Hermetic
Leads, Flexible	. . . . .	3
Minimum length	. . . . .	1.5"
Orientation and diameter	. . . . .	See Dimensional Outline

Terminal Diagram:

BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base



Lead 3 - Collector  
(Adjacent to red dot on side of case)

## CONVERTER

Maximum and Minimum Ratings, Absolute-Maximum Values:

DC COLLECTOR-TO-BASE VOLTAGE	. . . . .	-34 max.	volts
DC EMITTER-TO-BASE VOLTAGE	. . . . .	-0.5 max.	volt
DC COLLECTOR CURRENT	. . . . .	-10 max.	ma
DC EMITTER CURRENT	. . . . .	10 max.	ma



# 2N1639

## TRANSISTOR DISSIPATION:

At ambient temperature of 25° C. . . . .	80 max.	mw
At ambient temperature of 55° C. . . . .	50 max.	mw
At ambient temperature of 71° C. . . . .	35 max.	mw
AMBIENT TEMPERATURE (During operation) . . .	71 max.	°C
STORAGE-TEMPERATURE RANGE. . . . .	-65 to +85	°C

## Characteristics, At Ambient Temperature of 25° C:

### Common-Emitter Circuit, Base Input

DC Collector-to-Emitter Voltage. . . . .	-12	volts
DC Collector Current . . . . .	-1	ma
Collector-to-Base Capacitance (C <sub>ob</sub> ). . . . .	2 <sup>▲</sup>	μmf
Small-Signal Current Transfer Ratio at 1 kc. . . . .	75	

### Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage . . . . .	-12	volts
DC Collector Current . . . . .	-1	ma
Small-Signal Current Transfer Ratio at 1 kc. . . . .	0.986	
Alpha-Cutoff Frequency . . . . .	45	Mc

## Typical Operation, At Ambient Temperature of 25° C:

### In a common-emitter, base input, 1.5-Mc converter circuit

DC Collector-to-Emitter Voltage. . . . .	-5	-11	volts
DC Emitter Current . . . . .	0.65	0.65	ma
Input Resistance . . . . .	1850	2200	ohms
Output Resistance at 262.5 kc. . . . .	0.1	0.2	megohm
RMS Base-to-Emitter Oscillator-Injection Voltage . . . . .	100	100	mv
Useful Conversion Power Gain . . . . .	35.4	37	db

<sup>▲</sup> Maximum variation from this value is 0.9 μmf.

## OPERATING CONSIDERATIONS, DIMENSIONAL OUTLINE, and CURVES

shown under Type 2N1638 also apply to the 2N1639



## Mesa Transistor

### GERMANIUM P-N-P DIFFUSED-JUNCTION TYPE

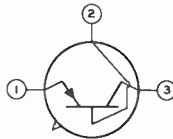
For High-Speed Switching Service in Commercial and Military Data-Processing Systems

#### GENERAL DATA

##### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter . . . . .	0.370"
Dimensional Outline . . . . .	JEDEC No. TO-5
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See Dimensional Outline
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector

#### SWITCHING SERVICE

##### Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	-13 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE . . . . .	-12 max.	volts
EMITTER-TO-BASE VOLTAGE <sup>a</sup> . . . . .	-4 max.	volts
COLLECTOR CURRENT . . . . .	-100 max.	ma
EMITTER CURRENT . . . . .	100 max.	ma

##### TRANSISTOR DISSIPATION:<sup>b</sup>

At ambient temperature of 25° C . . . . .	150 max.	mW
At ambient temperature of 55° C . . . . .	75 max.	mW
At ambient temperature of 71° C . . . . .	35 max.	mW

##### AMBIENT-TEMPERATURE RANGE:

Operating and storage . . . . .	-65 to +85	°C
---------------------------------	------------	----

##### LEAD TEMPERATURE:

For immersion in molten solder for 10 seconds maximum . . . . .	255 max.	°C
--	----------	----

##### Typical Operation:

In an inverter circuit at ambient temperature of 25° C

Collector-to-Emitter Voltage . . . . .	-5	volts
Base Resistor . . . . .	3000	ohms
Collector Resistor . . . . .	120	ohms
"Turn-On" Base Voltage . . . . .	-5	volts
"Turn-Off" Base Voltage . . . . .	5	volts
"On" Collector Current . . . . .	-40	ma

← Indicates a change.



# 2N1683

"Turn-On" Base Current . . . . .	-1.6	ma
"Turn-Off" Base Current . . . . .	1.6	ma
Switching Time:		
Delay time ( $t_d$ ) . . . . .	0.07	$\mu$ sec
Rise time ( $t_r$ ) . . . . .	0.06	$\mu$ sec
Storage time ( $t_s$ ) . . . . .	0.08	$\mu$ sec
Fall time ( $t_f$ ) . . . . .	0.05	$\mu$ sec

<sup>a</sup> This rating may be exceeded and the emitter-to-base junction operated in the breakdown condition provided the emitter dissipation is limited to 30 milliwatts at 25° C. For ambient temperatures above 25° C, the dissipation should be reduced by 0.5 milliwatt/°C.

<sup>b</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base unless otherwise specified. Ambient temperature of 25° C.

Min. Typical Max.

DC Collector Breakdown					
Voltage for dc collector ma. = -0.02, emitter open . $BV_{CBO}$					
	-13	-30	-		volts
DC Collector-to-Emitter Breakdown					
Voltage . . . . . $BV_{CERL}$					
	-12	-25	-		volts
DC Emitter Breakdown					
Voltage for dc emitter ma. = -0.1, collector open . . . $BV_{EBO}$					
	-4	-6	-		volts
DC Punch-Through					
Voltage . . . . . $V_P$					
	-12	-30	-		volts
DC Base-to-Emitter					
Voltage for dc collector ma. = -40, dc base ma. = -1 . . . $V_{BE}$					
	-	-0.4	-0.6		volt
DC Collector-Cutoff					
Current for collector volts = -6, emitter open . . . . . $I_{CBO}$					
	-	-1	-3		$\mu$ a
→ Collector Capacitance for dc collector volts = -6, emitter open . . . . . $C_C$					
	-	B	12		$\mu$ f
DC Current Transfer Ratio: $h_{FE}$					
With dc collector-to-emitter volts = -0.3, dc collector ma. = -10 . . .					
	50	75	-		
With dc collector-to-emitter volts = -0.5, dc collector ma. = -40 . . .					
	50	85	-		

→ Indicates a change.



Gain-Bandwidth Product <sup>c</sup> for dc collector-to-emitter volts = -3, dc collector ma. = -10 . . . . .	GBW	50	80	-	Mc
Thermal Resistance: Junction-to-free air. . . . .	$R_T$	-	-	400	°C/watt
Total Stored Charge: With dc collector ma. = -10, dc base ma. = -0.4. . . . .	$Q_S$	-	110	160	$\mu\text{coulombs}$
With dc collector ma. = -40, dc base ma. = -1.6. . . . .		-	200	410	$\mu\text{coulombs}$
Thermal Time Constant . . . . .	$\tau_1$	-	10	-	msec

<sup>c</sup> Frequency at which the current transfer ratio is equal to 1.

### OPERATING CONSIDERATIONS

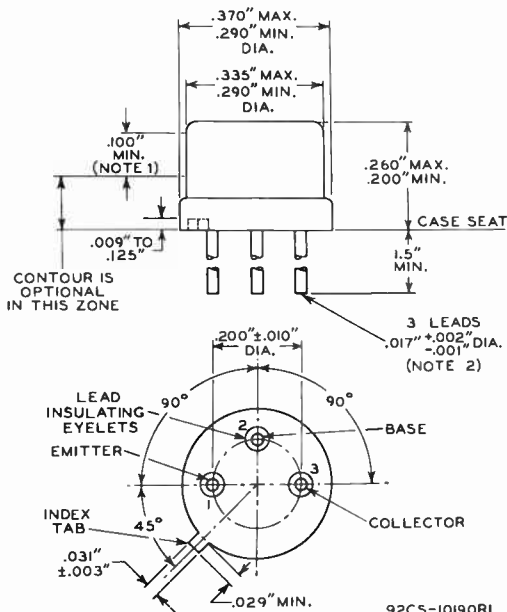
It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.



# 2N1683

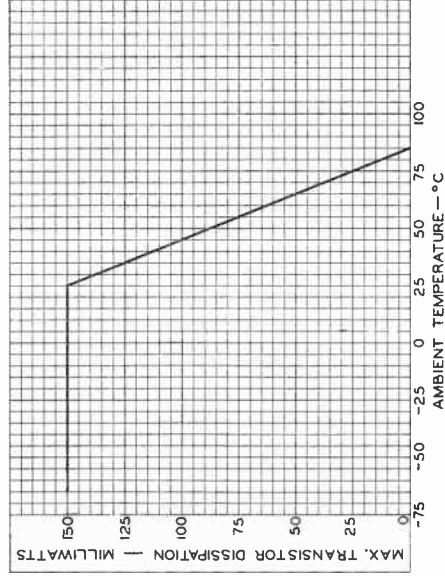
JEDEC No. T0-5



**NOTE 1:** THE DIAMETER IN THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE TOTAL VARIATION IN ACTUAL DIAMETER FROM THE TRUE DIAMETER, DUE TO TAPER AND OUT OF ROUND WITHIN THIS ZONE, WILL NOT EXCEED  $0.010''$ .

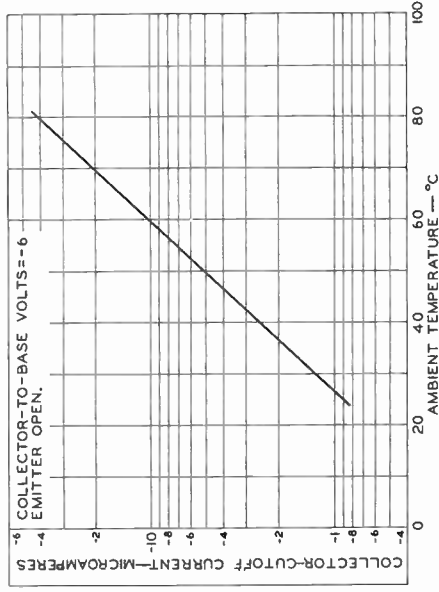
**NOTE 2:** THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN  $0.05''$  AND  $0.25''$  FROM THE CASE SEAT. BETWEEN  $0.25''$  AND  $1.5''$ , A MAXIMUM DIAMETER OF  $0.021''$  IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

## RATING CHART



92CS-10232RI

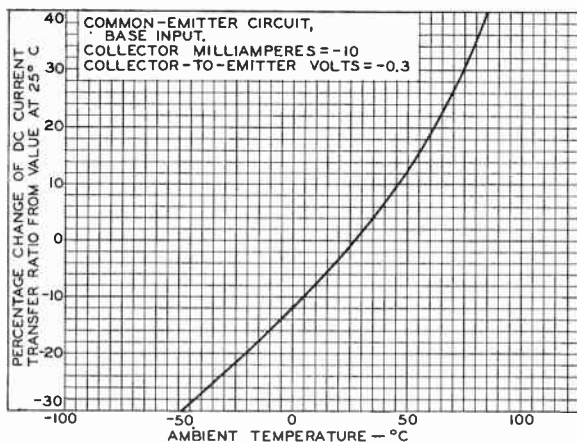
## TYPICAL COLLECTOR-CUTOFF-CURRENT CHARACTERISTIC



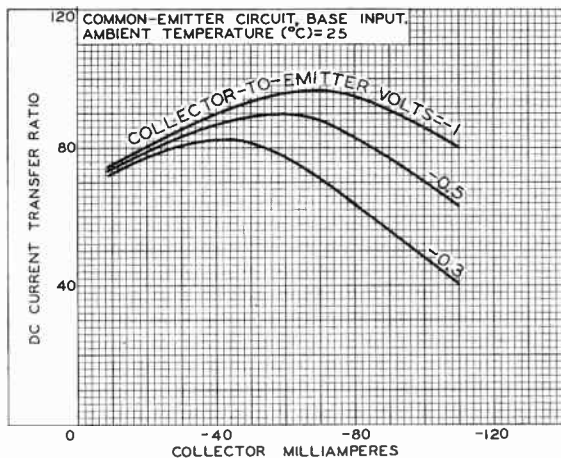
92CS-10213RI



## TYPICAL CHARACTERISTIC



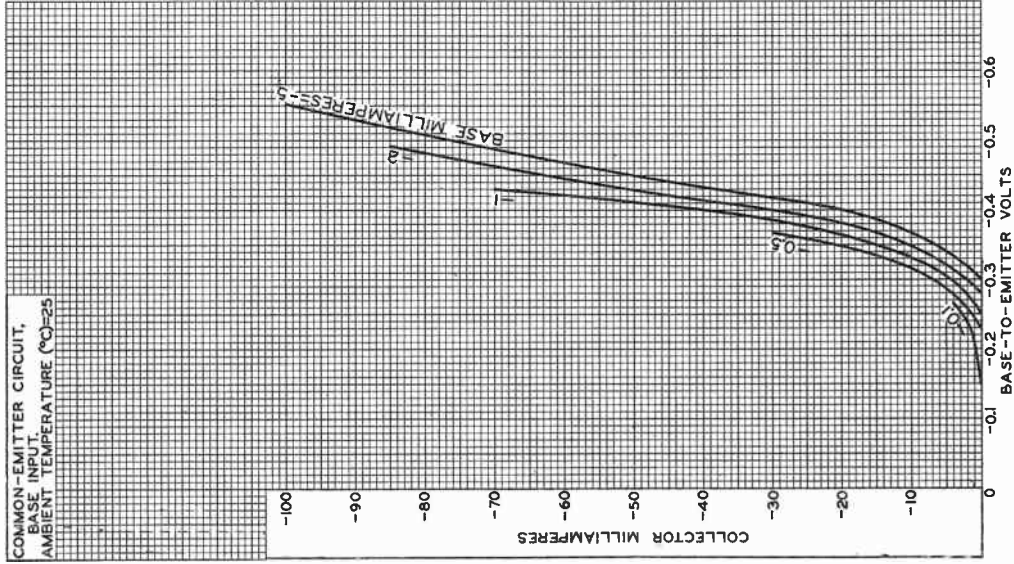
92CS-10199R3

TYPICAL DC CURRENT-  
TRANSFER-RATIO CHARACTERISTICS

92CS-10830



## TYPICAL TRANSFER CHARACTERISTICS



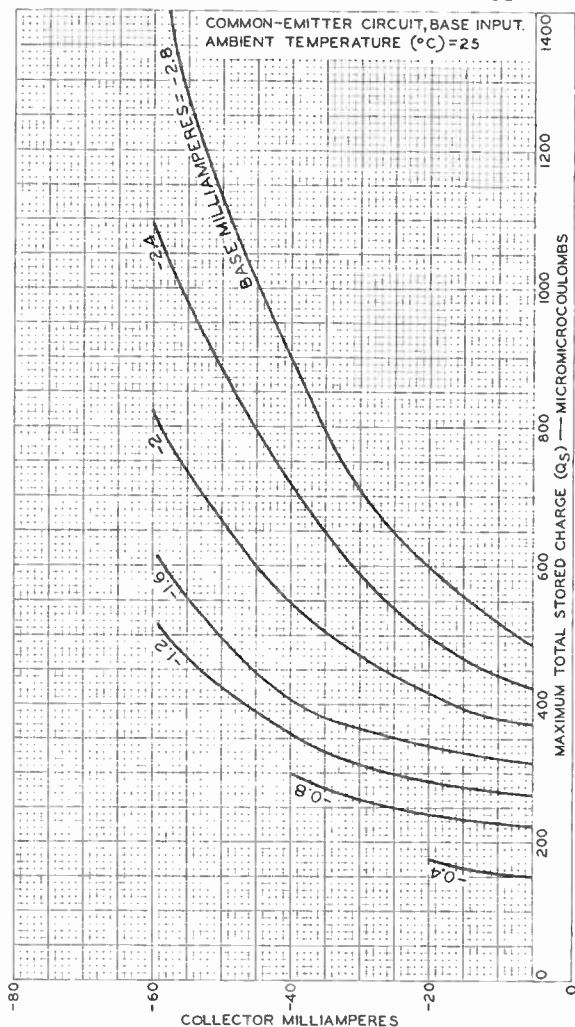
92CM-10229



RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division  
Somerville, N. J.

DATA 4  
4-61

# MAXIMUM TOTAL-STORED-CHARGE CHARACTERISTICS



92CM-10815

## Power Transistor

SILICON N-P-N DIFFUSED-JUNCTION TYPE  
For Industrial Applications

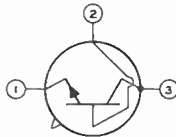
### GENERAL DATA

#### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter . . . . .	0.370"
Dimensional Outline . . . . .	JEDEC No. TO-5
Case . . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See Dimensional Outline
Terminal Diagram:	

BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector,  
Case

### INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and servo-amplifier, and relay-actuating circuits

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	60 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With emitter-to-base reverse biased (DC emitter-to-base volts = 1.5) . . . . .	60 max.	volts
With base open (Sustaining voltage) <sup>a</sup> . . . . .	40 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	6 max.	volts
COLLECTOR CURRENT . . . . .	1 max.	amp
BASE CURRENT . . . . .	0.75 max.	amp
TRANSISTOR DISSIPATION: <sup>b</sup>		
At case temperature of 25° C or below . . . . .	5 max.	watts
CASE-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +200	°C
LEAD TEMPERATURE:		
1/16" ± 1/32" from case		
for 10 seconds maximum . . . . .	255 max.	°C

#### Characteristics:

At case temperature of 25° C

Small-Signal Current Transfer Ratio ( $h_{fe}$ ) for dc collector-to-emitter volts = 4, dc collector ma. = 5 . . . . .	40
--	----



# 2N1700

Alpha-Cutoff Frequency ( $f_{\alpha b}$ ) for dc collector-to-base volts = 28, dc collector ma. = 5. . . . .	1.2	Mc
Collector-to-Base Capacitance ( $C_{ob}$ ) for dc collector-to-base volts = 40. . . . .	150	$\mu\mu\text{f}$
Thermal Time Constant ( $\tau_1$ ) . . . . .	10	msec

<sup>a</sup> The Collector-to-Emitter Sustaining Voltage ( $V_{CE0(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{\alpha M} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

<sup>b</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and case temperature of 25° C unless otherwise specified

	Min.	Max.	
DC Collector-to-Emitter Voltage: With emitter reverse bias volts = 1.5, dc collector ma. = 0.5. . . . .	$V_{CEX}$	60	- volts
With base open (Sustaining voltage), dc collector ma. = 50, dc base ma. = 0. . . . .	$V_{CE0(sus)}^a$	40	- volts
DC Base-to-Emitter Voltage for dc collector-to-emitter volts = 4, dc collector ma. = 100. . . . .	$V_{BE}$	-	2 volts
DC Collector-Cutoff Current for dc collector volts = 30, dc emitter ma. = 0, case temperature = 25° C. . . . .	$I_{CBO}$	-	75 $\mu\text{a}$
150° C. . . . .		-	1000 $\mu\text{a}$
DC Emitter-Cutoff Current for dc emitter volts = 6, dc collector ma. = 0 . . . . .	$I_{EBO}$	-	25 $\mu\text{a}$
DC Current Transfer Ratio for dc collector-to-emitter volts = 4, dc collector ma. = 100. . . . .	$h_{FE}$	20	80
DC Collector-to-Emitter Saturation Resistance for dc collector ma. = 100, dc base ma. = 10. . . . .	$R_S$	-	10 ohms
Thermal Resistance: Junction-to-case . . . . .	$R_T$	-	35 °C/watt
Junction-to-free air . . . . .		-	200 °C/watt

<sup>a</sup> The Collector-to-Emitter Sustaining Voltage ( $V_{CE0(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{\alpha M} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).



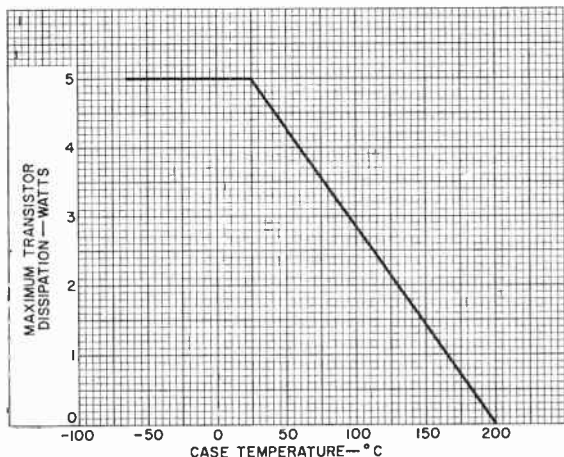
## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.

It is to be noted that the case of this transistor operates at the collector voltage. Consideration, therefore, should be given to the possibility of shock hazard, if the case of this transistor is to operate at a voltage appreciably above or below ground potential. In such cases, suitable precautionary measures should be taken.

## RATING CHART

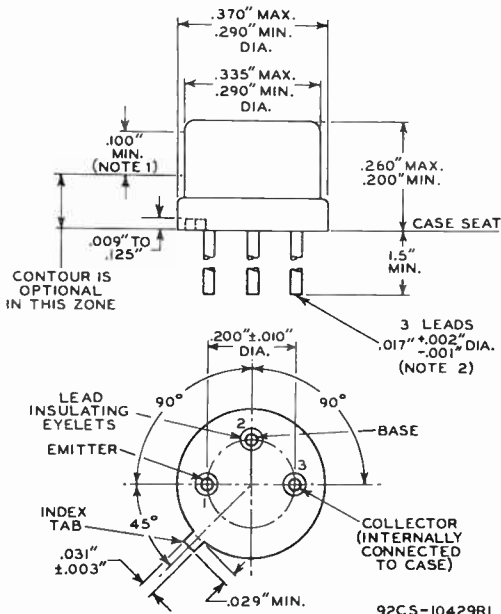


92CS-11019



# 2N1700

JEDEC No. T0-5



**NOTE 1:** THE DIAMETER IN THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE TOTAL VARIATION IN ACTUAL DIAMETER FROM THE TRUE DIAMETER, DUE TO TAPER AND OUT OR ROUND WITHIN THIS ZONE, WILL NOT EXCEED 0.010".

**NOTE 2:** THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE CASE SEAT. BETWEEN 0.25" AND 1.5", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

## Power Transistor

SILICON N-P-N DIFFUSED-JUNCTION TYPE  
For Industrial Applications

## GENERAL DATA

## Mechanical:

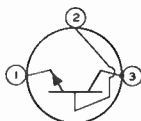
Operating Position. . . . .	Any
Maximum Overall Length. . . . .	0.770"
Maximum Seated Length. . . . .	0.330"
Maximum Diameter. . . . .	0.650"
Dimensional Outline. . . . .	JEDEC No. TO-8
Case. . . . .	Metal
Seals. . . . .	Hermetic

Terminal Diagram:

BOTTOM VIEW

Pin 1 - Emitter

Pin 2 - Base

Pin 3 - Collector,  
Case

## INDUSTRIAL SERVICE

*Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and servo-amplifier, and relay-actuating circuits*

## Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	60 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With emitter-to-base reverse biased (DC emitter-to-base volts = 1.5). . . . .	60 max.	volts
With base open (Sustaining voltage) <sup>a</sup> . . . . .	40 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	6 max.	volts
COLLECTOR CURRENT . . . . .	2.5 max.	amp
BASE CURRENT. . . . .	1 max.	amp
TRANSISTOR DISSIPATION: <sup>b</sup>		
At case temperature of 25° C or below . . . . .	25 max.	watts
CASE-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +175	°C
PIN TEMPERATURE:		
1/16" ± 1/32" from case for 10 seconds maximum. . . . .	235 max.	°C

## Characteristics:

*At case temperature of 25° C*

Alpha-Cutoff Frequency ( $f_{ab}$ ) for dc collector-to-base volts = 28, dc collector ma. = 5 . . . . .	1	Mc
Collector-to-Base Capacitance ( $C_{ob}$ ) with dc collector-to-base volts = 40. . . . .	175	$\mu\mu\text{f}$
Thermal Time Constant ( $\tau_1$ ). . . . .	10	msec



# 2N1701

<sup>a</sup> The Collector-to-Emitter Sustaining Voltage ( $V_{CE0(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{\alpha M} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

<sup>b</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## ELECTRICAL CHARACTERISTICS

*Voltage values are given with respect to base and case temperature of 25° C unless otherwise specified*

		Min.	Max.	
DC Collector-to-Emitter Voltage:				
With emitter reverse bias				
volts = 1.5, dc collector				
ma. = 0.75 . . . . .	$V_{CEX}$	60	-	volts
With base open (Sustaining				
voltage), dc collector				
ma. = 100, dc base ma. = 0 . . . . .	$V_{CE0}^a$ (sus)	40	-	volts
DC Base-to-Emitter Voltage for				
dc collector-to-emitter				
volts = 4, dc collector				
ma. = 300. . . . .	$V_{BE}$	-	3	volts
DC Collector-Cutoff Current	$I_{CBO}$			
for dc collector volts = 30,				
dc emitter ma. = 0, case				
temperature =				
25° C. . . . .		-	100	$\mu$ a
150° C. . . . .		-	1500	$\mu$ a
DC Emitter-Cutoff Current for				
dc emitter volts = 6, dc				
emitter ma. = 0. . . . .	$I_{EBO}$	-	50	$\mu$ a
DC Current Transfer Ratio				
for dc collector-to-emitter				
volts = 4, dc collector				
ma. = 300. . . . .	$h_{FE}$	20	80	
DC Collector-to-Emitter				
Saturation Resistance for				
dc collector ma. = 300, dc				
base ma. = 30. . . . .	$R_S$	-	5	ohms
Thermal Resistance:	$R_T$			
Junction-to-case . . . . .		-	7	°C/watt
Junction-to-free air . . . . .		-	100	°C/watt

<sup>a</sup> The Collector-to-Emitter Sustaining Voltage ( $V_{CE0(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{\alpha M} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.





Electrical connection can be made to the collector, base, and emitter pins by means of clips or by soldering directly to the pins. Soldering of connections to the pins may be made close to the pin seals provided care is taken to conduct excessive heat away from the pin seal, otherwise the heat of the soldering operation will crack the glass seals of the pins and damage the transistor.

Under no circumstances should the case be soldered to the heat sink because the heat of the soldering operation will permanently damage the transistor.

It is important that this transistor be securely fastened to a heat sink. A mounting clamp is provided for this purpose.

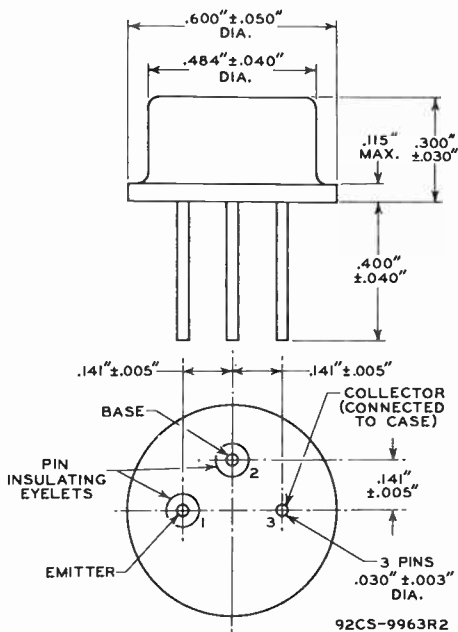
The chassis (heat sink) may be connected either to the positive or negative terminal of the voltage supply. In applications where the chassis is connected to the negative terminal of the voltage supply, it will be necessary to use an anodized-aluminum insulator having high thermal conductivity, or a 0.002" mica insulator between the transistor case and the chassis. The insulator should extend beyond the mounting clamp (See *Suggested Mounting Arrangement*). An aluminum washer should be drilled or punched to provide the two mounting holes, and the clearance holes for the collector, emitter, and base pins. The burrs should then be removed from the washer and the washer finally anodized. To insure that the anodized insulating layer is not destroyed during mounting, it will also be necessary to remove the burrs from the holes in the chassis. Furthermore, to prevent a short circuit between the mounting bolt and the chassis, it is important that an insulating washer be used between the bolt and the chassis.

It is to be noted that the case of this transistor operates at the collector voltage. Consideration therefore, should be given to the possibility of shock hazard if the case of this transistor is to operate at a voltage appreciably above or below ground potential. In such cases, suitable precautionary measures should be taken.

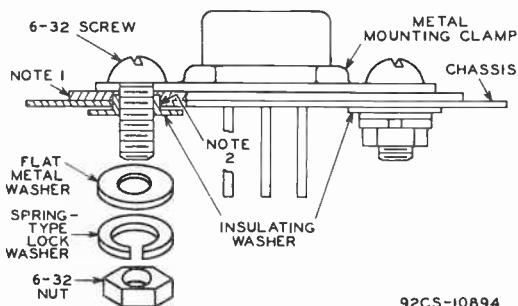


# 2N1701

JEDEC No. TO-8



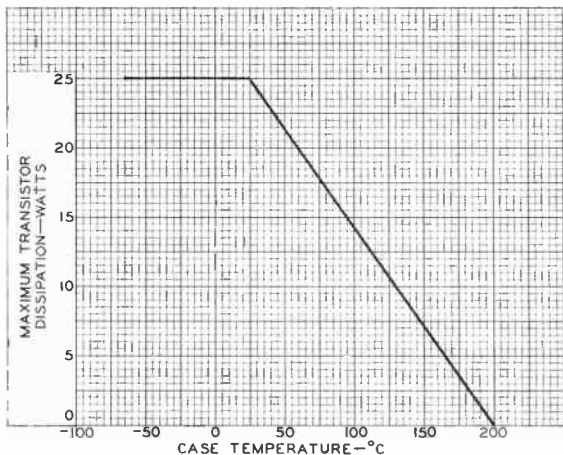
## SUGGESTED MOUNTING ARRANGEMENT



NOTE 1: 0.002" MICA INSULATOR OR ANODIZED ALUMINUM INSULATOR (DRILLED, OR PUNCHED WITH BURRS REMOVED).

NOTE 2: REMOVE BURRS FROM CHASSIS HOLES.

## RATING CHART



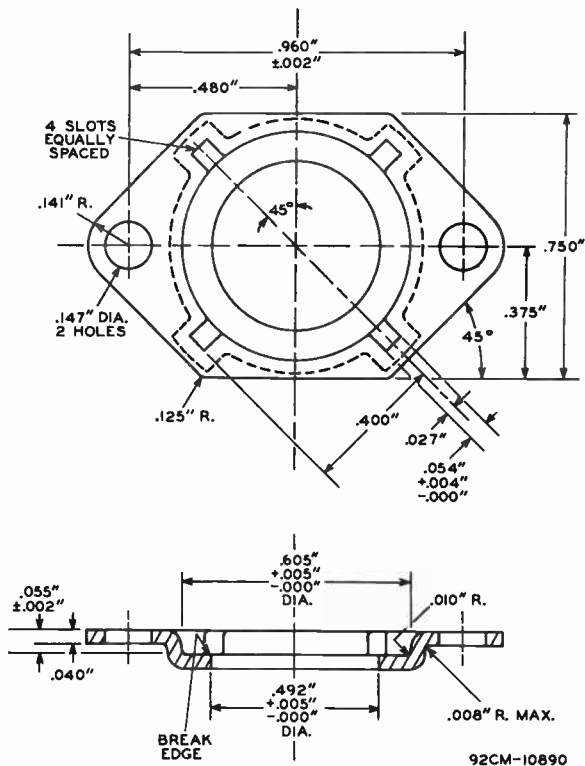
92CS-11014



# 2N1701

## MOUNTING CLAMP

Supplied with Each Transistor



## Power Transistor

SILICON N-P-N DIFFUSED-JUNCTION TYPE  
For Industrial Applications

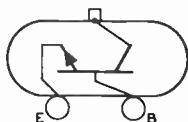
## GENERAL DATA

## Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	0.865"
Maximum Seated Length. . . . .	0.390"
Maximum Length of Mounting Flange. . . . .	1.550"
Maximum Width of Mounting Flange. . . . .	1.015"
Case. . . . .	Metal
Mounting Flange. . . . .	Metal
Seals. . . . .	Hermetic
Socket. . . . .	Loranger Mfg. Corp. No. 2149, or equivalent
Terminal Diagram (See <i>Dimensional Outline</i> ):	

E - Emitter

B - Base

MOUNTING FLANGE-  
Collector,  
Case

## INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter,  
chopper, voltage- and current-regulator, dc-  
and servo-amplifier, and relay-actuating circuits

## Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	60 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With emitter-to-base reverse biased (DC emitter-to-base volts = 1.5). . . . .	60 max.	volts
With base open (Sustaining voltage) <sup>a</sup> . . . . .	40 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	6 max.	volts
COLLECTOR CURRENT . . . . .	5 max.	amp
BASE CURRENT. . . . .	2.5 max.	amp
TRANSISTOR DISSIPATION: <sup>b</sup>		
At mounting-flange temperature of 25° C or below. . . . .	75 max.	watts
MOUNTING-FLANGE TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +200	°C

## Characteristics:

At mounting-flange temperature of 25° C

Alpha-Cutoff Frequency ( $f_{ab}$ ) with dc collector-to-base volts = 28, dc collector ma. = 5. . . . .	1	Mc
Collector-to-Base Capacitance ( $C_{ob}$ ) with dc collector-to-base volts = 40. . . . .	200	$\mu\mu\text{f}$
Thermal Time Constant ( $\tau_1$ ). . . . .	12	msec



<sup>a</sup> The Collector-to-Emitter Sustaining Voltage ( $V_{CE0(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{\alpha M} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

<sup>b</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and mounting-flange temperature of 25° C unless otherwise specified

	Min.	Max.	
DC Collector-to-Emitter Voltage:			
With emitter reverse bias			
volts = 1.5, dc collector ma. = 1 . . . . .	$V_{CEX}$	60	- volts
With base open (Sustaining voltage), dc collector ma. = 100, dc base ma. = 0. . . . .	$V_{CE0}^a$ (sus)	40	- volts
DC Base-to-Emitter Voltage for dc collector-to-emitter volts = 4, dc collector ma. = 800 . . . . .	$V_{BE}$	-	4 volts
DC Collector-Cutoff Current for dc collector volts = 30, dc emitter ma. = 0, mounting-flange temperature = 25° C . . . . .	$I_{CBO}$	-	200 $\mu a$
150° C. . . . .		-	2000 $\mu a$
DC Emitter-Cutoff Current for dc emitter volts = 6, dc collector ma. = 0 . . . . .	$I_{EBO}$	-	100 $\mu a$
DC Current Transfer Ratio for dc collector-to-emitter volts = 4, dc collector ma. = 800 . . . . .	$h_{FE}$	1.5	60
DC Collector-to-Emitter Saturation Resistance for dc collector ma. = 800, dc base ma. = 80. . . . .	$R_S$	-	4 ohms
Thermal Resistance: Junction-to-mounting-flange . . . . .	$R_T$	-	2.33 °C/watt

<sup>a</sup> The Collector-to-Emitter Sustaining Voltage ( $V_{CE0(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{\alpha M} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.



This transistor utilizes the Loranger Mfg. Corp. socket No. 2149, or equivalent. Electrical connection can also be made to the base and emitter pins by soldering directly to the pins. Soldering of connections to the pins may be made close to the pin seals provided care is taken to conduct excessive heat away from the pin seal, otherwise the heat of the soldering operation will crack the glass seals of the pins and damage the transistor.

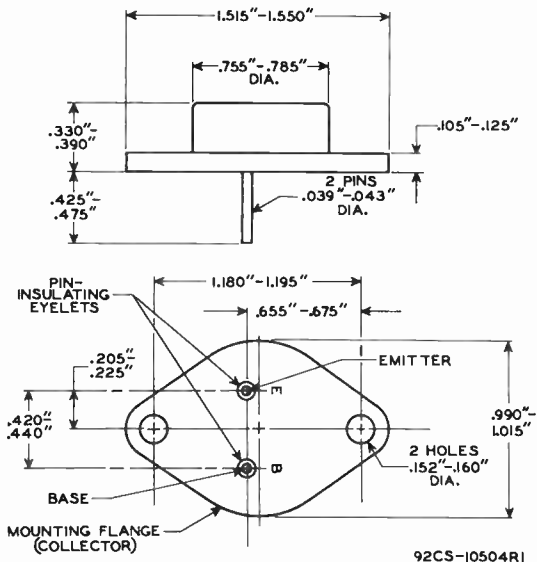
Under no circumstances should the mounting flange be soldered to the heat sink because the heat of the soldering operation will permanently damage the transistor.

It is important that the mounting flange which serves as the collector terminal be securely fastened to a heat sink. Depending on the application, the chassis (heat sink) may be connected either to the positive or negative terminal of the voltage supply.

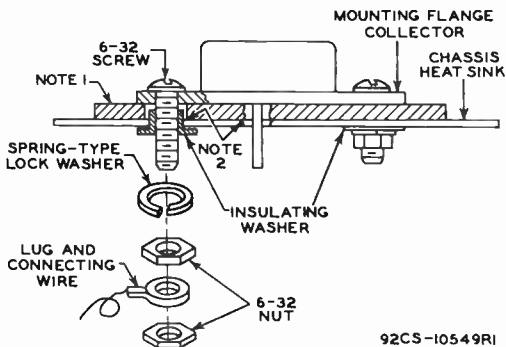
In applications where the chassis is connected to the negative terminal of the voltage supply, it will be necessary to use an anodized-aluminum insulator having high thermal conductivity, or a 0.002" mica insulator between the mounting flange and the chassis. An aluminum washer should be drilled or punched to provide the two mounting holes, and the clearance holes for the emitter and base pins. The burrs should then be removed from the washer and the washer finally anodized. To insure that the anodized insulating layer is not destroyed during mounting, it will also be necessary to remove the burrs from the holes in the chassis. Furthermore, to prevent a short circuit between the mounting bolt and the chassis, it is important that an insulating washer be used between the bolt and the chassis (See *Suggested Mounting Arrangement*).

It is to be noted that the case of this transistor operates at the collector voltage. Consideration, therefore, should be given to the possibility of shock hazard, if the case of this transistor is to operate at a voltage appreciably above or below ground potential. In such cases, suitable precautionary measures should be taken.





## SUGGESTED MOUNTING ARRANGEMENT

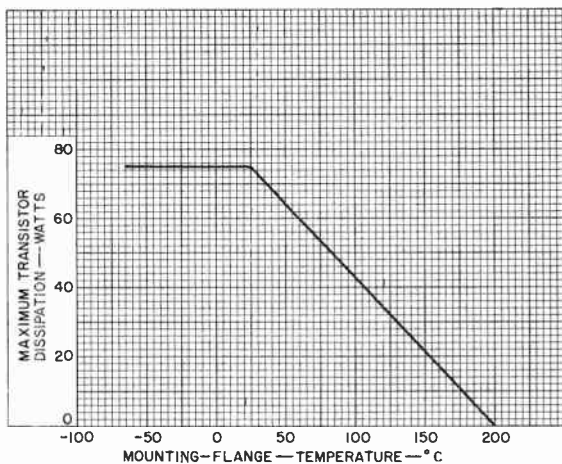


NOTE 1: 0.002" MICA INSULATOR OR ANODIZED-ALUMINUM INSULATOR (DRILLED, OR PUNCHED WITH BURRS REMOVED).

NOTE 2: REMOVE BURRS FROM CHASSIS HOLES.



## RATING CHART



92CS-11015





## Power Transistor

SILICON N-P-N DIFFUSED-JUNCTION TYPE

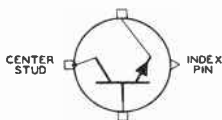
For Industrial Applications

### GENERAL DATA

#### Mechanical:

Operating Position. . . . .	Any
Maximum Overall Length. . . . .	1.230"
Maximum Seated Length. . . . .	0.520"
Maximum Diameter. . . . .	1.250"
Dimensional Outline. . . . .	JEDEC No. TO-36
Case. . . . .	Welded, Metal
Seals. . . . .	Hermetic
Terminal Diagram (See <i>Dimensional Outline</i> ):	

BOTTOM VIEW



### INDUSTRIAL SERVICE

*Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and servo-amplifier, and relay-actuating circuits*

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	60 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With emitter-to-base reverse biased (DC emitter-to-base volts = 1.5). . . . .	60 max.	volts
With base open (Sustaining voltage) <sup>a</sup> . . . . .	40 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	6 max.	volts
COLLECTOR CURRENT . . . . .	5 max.	amp
BASE CURRENT. . . . .	2.5 max.	amp
TRANSISTOR DISSIPATION: <sup>b</sup>		
At case temperature of 25° C or below . . . . .	75 max.	watts
CASE-TEMPERATURE RANGE:		
Operating and storage . . . . .	-65 to +200	°C

#### Characteristics:

*At case temperature of 25° C*

Alpha-Cutoff Frequency ( $f_{ab}$ )		
with dc collector-to base volts		
= .78, dc collector ma. = 5. . . . .	1	Mc
Collector-to-Base Capacitance ( $C_{ob}$ )		
with dc collector-to-base volts = 40. . . . .	200	$\mu\mu\text{f}$
Thermal Time Constant ( $\tau_1$ ). . . . .	12	msec



# 2N1703

- <sup>a</sup> The Collector-to-Emitter Sustaining Voltage ( $V_{CEQ(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{\alpha M} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity.
- <sup>b</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and case temperature of 25° C unless otherwise specified

	Min.	Max.	
DC Collector-to-Emitter Voltage: With emitter reverse-bias volts = 1.5, dc collector ma. = 1. . . . . $V_{CEX}$	60	-	volts
With base open (Sustaining voltage), dc collector ma. = 100, dc base ma. = 0 . . . . . $V_{CEQ(sus)}^a$	40	-	volts
DC Base-to-Emitter Voltage for dc collector-to-emitter volts = 4, dc collector ma. = 800. . . . . $V_{BE}$	-	4	volts
DC Collector-Cutoff Current for dc collector volts = 30, dc emitter ma. = 0, case temperature = 25° C . . . . .	-	200	$\mu$ a
150° C . . . . .	-	2000	$\mu$ a
DC Emitter-Cutoff Current for dc emitter volts = 6, dc collector ma. = 0. . . . . $I_{EBO}$	-	100	$\mu$ a
DC Current Transfer Ratio for dc collector-to-emitter volts = 4, dc collector ma. = 800 . . . . . $h_{FE}$	15	60	
DC Collector-to-Emitter Saturation Resistance for dc collector ma. = 800, dc base ma. = 80 . . . . . $R_S$	-	4	ohms
Thermal Resistance: Junction-to-case . . . . . $R_T$	-	2.33	°C/watt

- <sup>a</sup> The Collector-to-Emitter Sustaining Voltage ( $V_{CEQ(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{\alpha M} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity.

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

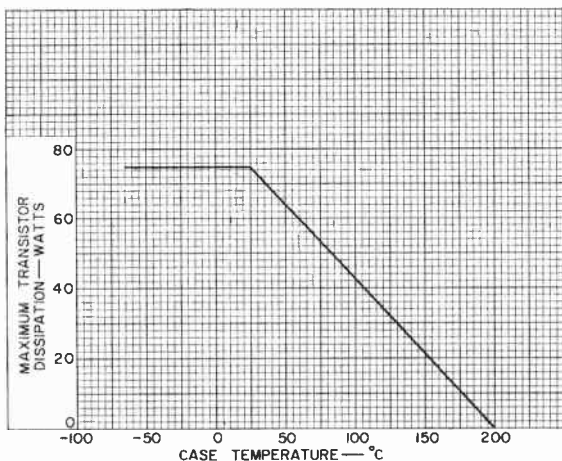


Electrical connection can be made to the base and emitter terminals by means of clips or by soldering directly to the terminals. When soldering connections are made to the terminals, care should be taken to conduct excessive heat away from the terminal seals, otherwise the heat of the soldering operation will crack the glass seals of the terminals and damage the transistor.

This transistor is provided with a single-ended stud for mounting to a heat sink and for electrical connection to the collector. (See accompanying *Suggested Mounting Arrangement*). Electrical connection to the base and to the emitter is made to their respective terminals.

It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.

## RATING CHART

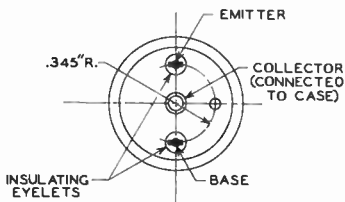
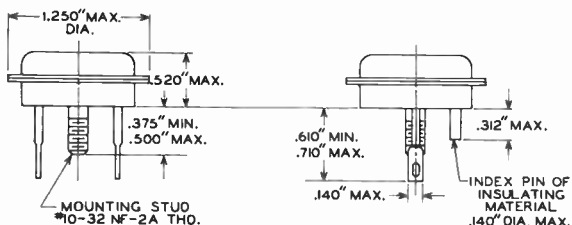


92CS-11016



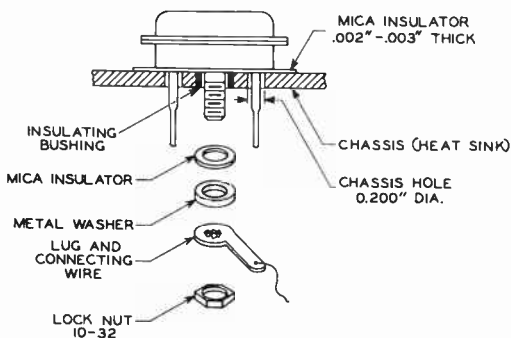
# 2N1703

JEDEC No. T0-36



92CM-10612RI

## SUGGESTED MOUNTING ARRANGEMENT



92CS-10624RI

## Transistor

### SILICON N-P-N DOUBLE-DIFFUSED-JUNCTION EPITAXIAL-PLANAR TYPE

For Switching Applications in  
Industrial and Military Equipment

#### GENERAL DATA

##### Mechanical:

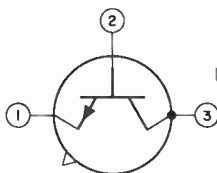
Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.080"
Maximum Diameter . . . . .	0.230"
Dimensional Outline . . . . .	JEDEC No. TO-46
Case . . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	0.500"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>

Terminal Diagram:

BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base



Lead 3 - Collector,  
Case

#### SWITCHING SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values:*

##### COLLECTOR-TO-BASE VOLTAGE:

With emitter open . . . . .  $V_{CBO}$  25 max. volts

##### COLLECTOR-TO-EMITTER VOLTAGE:

With external resistance between  
base and emitter (ohms)  
= 1000, load resistance  
(ohms) = 100 . . . . .  $V_{CERL}$  20 max. volts

##### EMITTER-TO-BASE VOLTAGE:

With collector open . . . . .  $V_{EBO}$  3 max. volts

COLLECTOR CURRENT . . . . .  $I_C$  0.2 max. amp

##### TRANSISTOR DISSIPATION:<sup>a</sup>

At case temperature<sup>b</sup> of 25° C  
or below . . . . . 1 max. watt

At free-air temperature of 25° C  
or below . . . . . 0.3 max. watt

##### TEMPERATURE RANGE:

Storage . . . . . -65 to +300 °C

Operating . . . . . -65 to +175 °C

##### LEAD TEMPERATURE:<sup>c</sup>

For 10 seconds maximum . . . . . 235 max. °C

<sup>a</sup> See accompanying Rating Chart.



# 2N1708

<sup>b</sup> Measured at center of seating plane.

<sup>c</sup> Measured  $1/16" \pm 1/32"$  down from seating plane.

## ELECTRICAL CHARACTERISTICS

*Voltage values are given with respect to base and free-air temperature of 25° C unless otherwise specified*

		Max.	Max.	
DC Collector Breakdown Voltage for dc collector ma. = 0.1, emitter ma. = 0. . . . .	$BV_{CBO}$	25	-	volts
DC Emitter Breakdown Voltage for dc emitter ma. = 0.1, collector ma. = 0. . . . .	$BVEBO$	3	-	volts
→ DC Collector-to-Emitter Latching Voltage <sup>d</sup> for external resistance between base and emitter (ohms) = 1000, load resistance (ohms) = 100. . . . .	$V_{CERL}$	20	-	volts
DC Base-to-Emitter Saturation Voltage for dc collector ma. = 10, dc base ma. = 1. . . . .	$V_{BE(sat)}$	0.7	0.9	volt
DC Collector-to-Emitter Saturation Voltage: With dc collector ma. = 10, dc base ma. = 1. . . . .	$V_{CE(sat)}$	-	0.22	volt
With dc collector ma. = 50, dc base ma. = 5. . . . .		-	0.35	volt
DC Collector-Cutoff Current for dc collector volts = 15, emitter ma. = 0, free-air temperature =	$I_{BCO}$			
25° C. . . . .		-	0.025	$\mu a$
150° C. . . . .		-	15	$\mu a$
DC Collector Current for base- to-emitter forward bias volts = 0.35, dc collector-to- emitter volts = 10, free-air temperature = 100° C. . . . .	$I_{CEX}$	-	15	$\mu a$
→ Collector-to-Base Capacitance for dc collector volts = 10, emitter ma. = 0, frequency (kc) = 140 . . . . .	$C_{ob}$	-	6	pf
DC Current Transfer Ratio for dc collector to emitter volts = 1, dc collector ma. = 10 . . . .	$h_{FE}$	20	-	
Small-Signal Current Transfer Ratio for dc collector-to- emitter volts = 10, dc collector ma. = 10, frequency (Mc) = 100 . . . . .	$h_{fe}$	2	-	

→ Indicates a change.





Storage Time <sup>e</sup> for dc collector supply volts = 10, collector resistance (ohms) = 1000, turn-on and turn-off dc base ma. = 10 each, dc collector ma. = 10. . . . .	$t_s$	-	25	nsec	←
Turn-On Time <sup>f</sup> (Delay time + rise time) for dc collector supply volts = 3, turn-on dc base ma. = 3, turn-off dc base ma. = 1, dc collector ma. = 10 . . . . .	$t_d + t_r$	-	40	nsec	←
Turn-Off Time <sup>f</sup> (Storage time + fall-time) for dc collector supply volts = 3, turn-on dc base ma. = 3, turn-off dc base ma. = 1, dc collector ma. = 10. . . . .	$t_s + t_f$		75	nsec	←

<sup>d</sup> For description of this test, write to Commercial Engineering, Semiconductor & Materials Division, RCA, Somerville, New Jersey.

<sup>e</sup> See accompanying *Storage-Time-Measurement Circuit*.

<sup>f</sup> See accompanying *Turn-On-Time and Turn-Off-Time Measurement Circuit*.

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the seating plane provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.

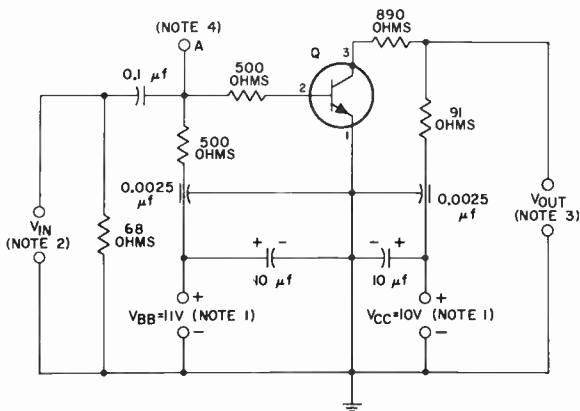
It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.

← Indicates a change.



# 2N1708

## STORAGE-TIME-MEASUREMENT CIRCUIT



92CS-11226R2

Q: Transistor type 2N1708

NOTE 1: WITH CERTAIN TYPES OF POWER SUPPLIES, IT MAY BE NECESSARY TO CONNECT 25- $\mu$ f DECOUPLING CAPACITORS ACROSS THE POWER-SUPPLY TERMINALS FOR  $V_{CC}$  AND  $V_{BB}$ .

NOTE 2: INPUT VOLTAGE ( $V_{IN}$ ) OBTAINED FROM MERCURY-RELAY-TYPE PULSE GENERATOR HAVING AN OUTPUT IMPEDANCE OF 50 OHMS.

NOTE 3: THE ASSOCIATED INPUT AND OUTPUT WAVE FORMS SHOULD BE MONITORED BY MEANS OF A SAMPLING OSCILLOSCOPE HAVING AN INPUT IMPEDANCE OF 50 OHMS.

NOTE 4: TEST POINT FOR OBSERVATION OF REFERENCE PULSE VOLTAGE ( $V_A$ ).

## Transistor

## SILICON N-P-N DOUBLE-DIFFUSED-JUNCTION EPITAXIAL-PLANAR TYPE

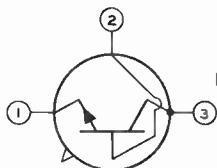
For Switching Applications in  
Industrial and Military Equipment

## GENERAL DATA

## Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.080"
Maximum Diameter . . . . .	0.230"
Dimensional Outline . . . . .	JEDEC No. TO-46
Case . . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	0.500"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector,  
Case

## SWITCHING SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values*:

## COLLECTOR-TO-BASE VOLTAGE:

With emitter open . . . . . 25 max. volts

## COLLECTOR-TO-EMITTER VOLTAGE:

With external resistor ( $\text{ohms}$ ) = 10

between base and emitter . . . . . 20 max. volts

## EMITTER-TO-BASE VOLTAGE:

With collector open . . . . . 3 max. volts

COLLECTOR CURRENT . . . . . 0.2 max. amp

TRANSISTOR DISSIPATION:<sup>a</sup>

At case temperature<sup>b</sup> of 25°C or below . . . . . 1 max. watt

At free-air temperature of 25°C or below . . . . . 0.3 max. watt

## TEMPERATURE RANGE:

Storage . . . . . -65 to +300 °C

Operating . . . . . -65 to +175 °C

LEAD TEMPERATURE:<sup>c</sup>

For 10 seconds maximum . . . . . 235 max. °C

<sup>a</sup> See accompanying *Rating Chart*.

<sup>b</sup> Measured at center of seating plane.

<sup>c</sup> Measured 1/16" ± 1/32" down from seating plane.



# 2N1708

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and free-air temperature of 25° C unless otherwise specified.

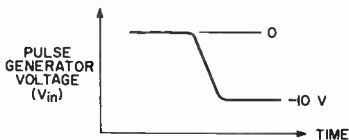
		Min.	Max.	
DC Collector Breakdown Voltage for dc collector ma. = 0.1, emitter ma. = 0 . . . . .	$BV_{CBO}$	25	-	volts
DC Collector-to-Emitter Breakdown Voltage for dc collector ma. = 50, external base-to-emitter resistor (ohms) = 10 . . . . .	$BV_{CER}$	20	-	volts
DC Emitter Breakdown Voltage for dc emitter ma. = 0.1, collector ma. = 0 . . . . .	$BV_{EBO}$	3	-	volts
DC Base-to-Emitter Saturation Voltage for dc collector ma. = 10, dc base ma. = 1 . . . . .	$V_{BE}(sat)$	0.7	0.9	volt
DC Collector-to-Emitter Saturation Voltage:	$V_{CE}(sat)$			
With dc collector ma. = 10, dc base ma. = 1 . . . . .		-	0.22	volt
With dc collector ma. = 50, dc base ma. = 5 . . . . .		-	0.35	volt
DC Collector-Cutoff Current for dc collector volts = 15, emitter ma. = 0, free-air temperature =	$I_{BCO}$			
25° C . . . . .		-	0.025	$\mu a$
150° C . . . . .		-	15	$\mu a$
DC Collector Current for base-to-emitter forward bias volts = 0.35, dc collector-to-emitter volts = 10, free-air temperature = 100° C . . . . .	$I_{CEX}$	-	15	$\mu a$
Collector-to-Base Capacitance for dc collector volts = 10, emitter ma. = 0, frequency (kc) = 140 . . . . .	$C_{ob}$	-	6	$\mu f$
Small-Signal Current Transfer Ratio for dc collector-to-emitter volts = 10, dc collector ma. = 10, frequency (Mc) = 100 . . . . .	$h_{fe}$	2	-	
DC Current Transfer Ratio for dc collector to emitter volts = 1, dc collector ma. = 10 . . . . .	$h_{FE}$	20	-	
Storage Time <sup>d</sup> for dc collector supply volts = 10, collector resistor (ohms) = 1000, "turn-on" and "turn-off" base ma. = 10 each, dc collector ma. = 10 . . . . .	$t_s$	-	25	$\mu sec$

<sup>d</sup> See accompanying Storage-Time-Measurement Circuit.



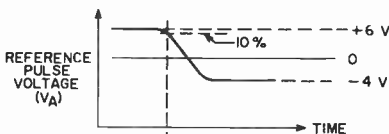


## ASSOCIATED WAVE FORMS

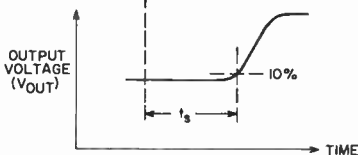


RISE TIME  $< 1 \mu\text{SEC}$   
 PULSE DURATION  $\geq 300 \mu\text{SEC}$   
 DUTY FACTOR  $< 0.02$

*INPUT WAVE FORM*



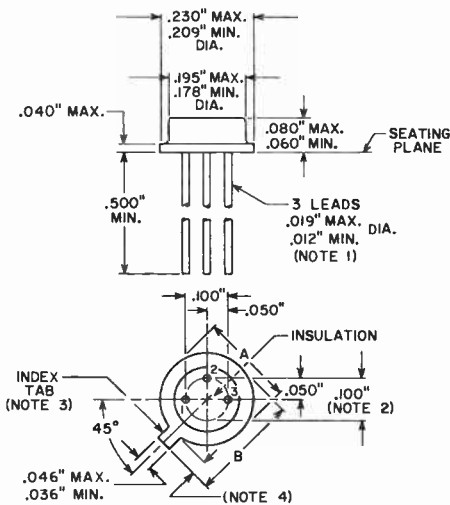
*REFERENCE WAVE FORM OBSERVED AT POINT "A" IN STORAGE-TIME-MEASUREMENT CIRCUIT*



*OUTPUT WAVE FORM*

92CS-11224

JEDEC No. TO-46



92CS-11225

NOTE 1: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE SEATING PLANE. BETWEEN 0.25" TO THE END OF THE LEAD, A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

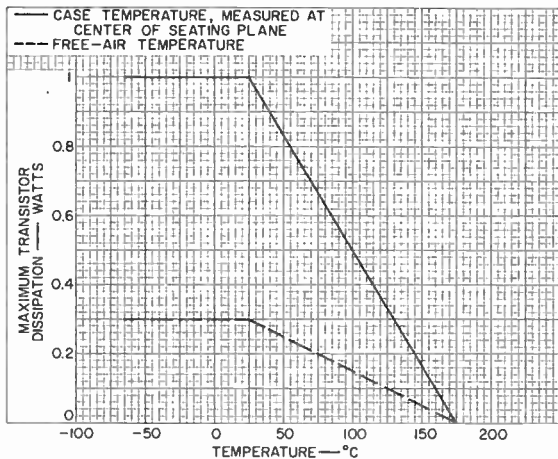
NOTE 2: MAXIMUM DIAMETER LEADS AT A GAUGING PLANE  $0.054'' + 0.001'' - 0.000''$  BELOW SEATING PLANE TO BE WITHIN  $0.007''$  OF THEIR TRUE LOCATION RELATIVE TO MAXIMUM WIDTH TAB AND TO THE  $0.230''$  MAXIMUM DIAMETER MEASURED WITH A SUITABLE GAUGE. WHEN GAUGE IS NOT USED, MEASUREMENT WILL BE MADE AT SEATING PLANE.

NOTE 3: INDEX TAB FOR VISUAL ORIENTATION ONLY.

NOTE 4: TAB LENGTH TO BE  $0.028''$  MINIMUM -  $0.046''$  MAXIMUM AND WILL BE DETERMINED BY SUBTRACTING DIAMETER "A" FROM DIMENSION "B".



## RATING CHART

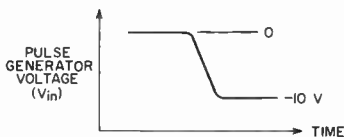


92CS-11223



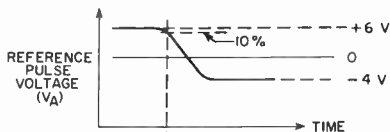


## ASSOCIATED WAVE FORMS

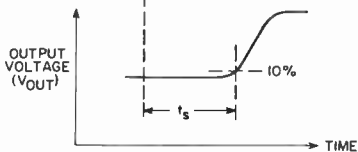


RISE TIME  $< 1\text{ m}\mu\text{SEC}$   
 PULSE DURATION  $\geq 300\text{ m}\mu\text{SEC}$   
 DUTY FACTOR  $< 0.02$

INPUT WAVE FORM



REFERENCE WAVE FORM OBSERVED AT POINT "A" IN STORAGE-TIME-MEASUREMENT CIRCUIT



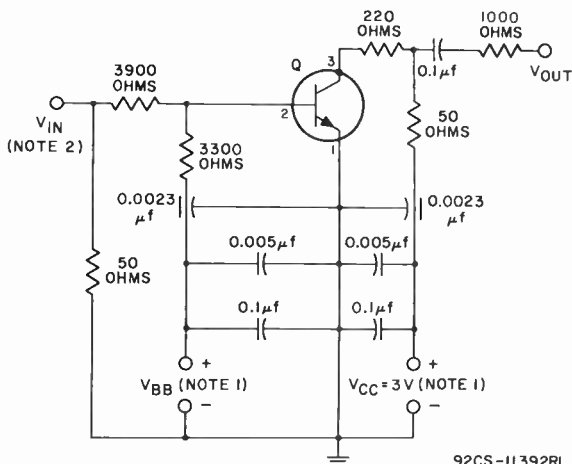
OUTPUT WAVE FORM

92CS-11224



# 2N1708

## TURN-ON-TIME AND TURN-OFF-TIME MEASUREMENT CIRCUIT



Q: Transistor type 2N1708

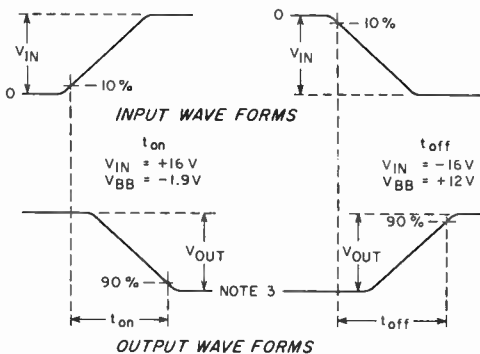
NOTE 1: WITH CERTAIN TYPES OF POWER SUPPLIES, IT MAY BE NECESSARY TO CONNECT 25- $\mu$ f DECOUPLING CAPACITORS ACROSS THE POWER-SUPPLY TERMINALS FOR  $V_{CC}$  AND  $V_{BB}$ .

NOTE 2: INPUT VOLTAGE ( $V_{IN}$ ) OBTAINED FROM MERCURY-RELAY TYPE PULSE GENERATOR HAVING AN OUTPUT IMPEDANCE OF 50 OHMS.

NOTE 3: INPUT AND OUTPUT WAVE FORMS, SHOWN ON NEXT PAGE, SHOULD BE MONITORED BY MEANS OF A SAMPLING OSCILLOSCOPE HAVING AN INPUT IMPEDANCE OF 50 OHMS.

NOTE 4: ALL RESISTANCE VALUES HAVE  $\pm 1\%$  TOLERANCE.

## ASSOCIATED WAVE FORMS

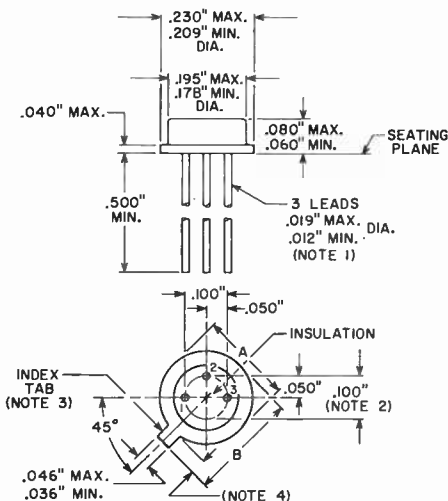


92CS-11393



# 2N1708

JEDEC No. T0-46



92CS-11225

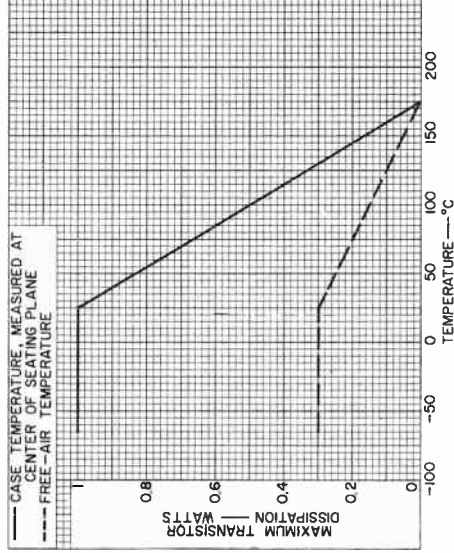
NOTE 1: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE SEATING PLANE. BETWEEN 0.25" TO THE END OF THE LEAD, A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

NOTE 2: MAXIMUM DIAMETER LEADS AT A GAUGING PLANE 0.054" + 0.001" - 0.000" BELOW SEATING PLANE TO BE WITHIN 0.007" OF THEIR TRUE LOCATION RELATIVE TO MAXIMUM WIDTH TAB AND TO THE 0.230" MAXIMUM DIAMETER MEASURED WITH A SUITABLE GAUGE. WHEN GAUGE IS NOT USED, MEASUREMENT WILL BE MADE AT SEATING PLANE.

NOTE 3: INDEX TAB FOR VISUAL ORIENTATION ONLY.

NOTE 4: TAB LENGTH TO BE 0.028" MINIMUM - 0.048" MAXIMUM AND WILL BE DETERMINED BY SUBTRACTING DIAMETER "A" FROM DIMENSION "B".

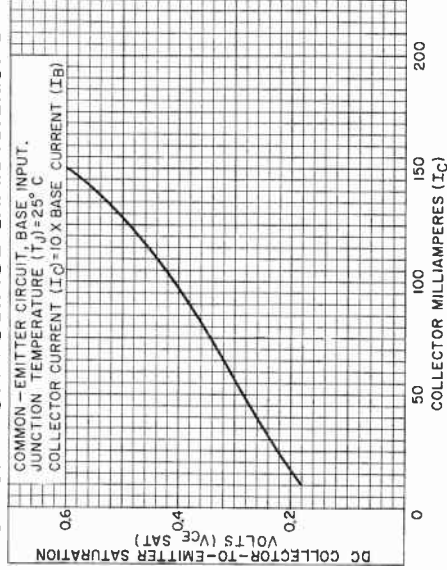
## RATING CHART



World Precision History

92CS-11223

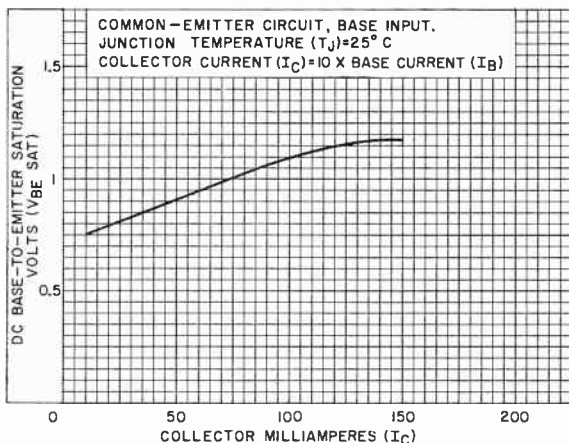
## TYPICAL DC COLLECTOR-TO-EMITTER SATURATION-VOLTAGE CHARACTERISTIC



92CS-11377

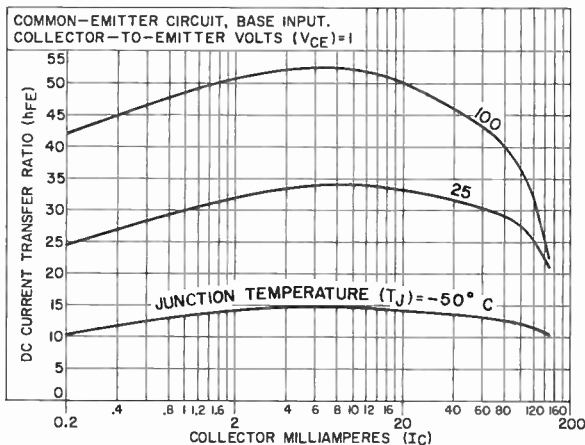


## TYPICAL DC BASE-TO-EMITTER SATURATION-VOLTAGE CHARACTERISTIC



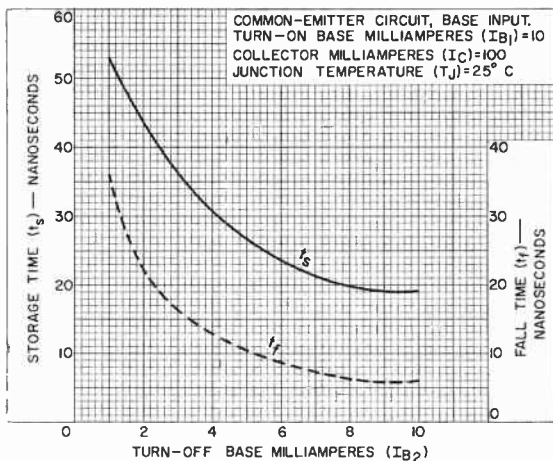
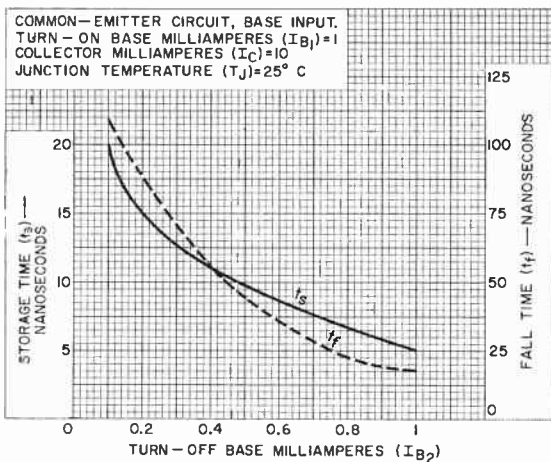
92CS-11378

## TYPICAL DC CURRENT-TRANSFER-RATIO CHARACTERISTICS

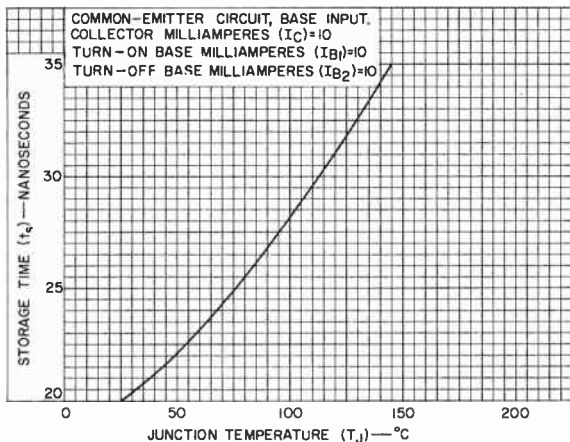


92CS-11391

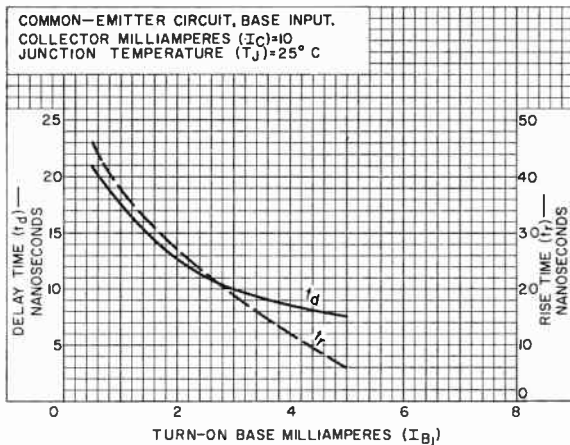
## TYPICAL STORAGE-TIME AND FALL-TIME CHARACTERISTICS



## TYPICAL STORAGE-TIME CHARACTERISTIC

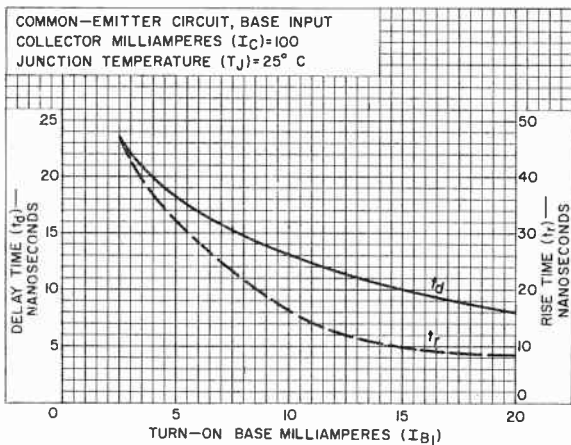


## TYPICAL DELAY-TIME AND RISE-TIME CHARACTERISTICS





## TYPICAL DELAY-TIME AND RISE-TIME CHARACTERISTICS



92CS-11389



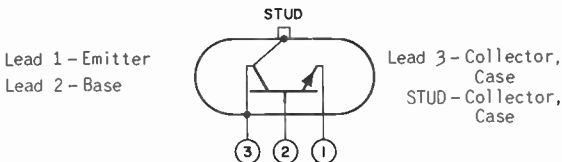


## Power Transistor

SILICON N-P-N DIFFUSED-JUNCTION TYPE  
For Industrial Applications

### Mechanical:

Operating Position. . . . .	Any
Maximum Length. . . . .	See <i>Dimensional Outline</i>
Maximum Diameter. . . . .	0.460"
Case. . . . .	Metal
Seals. . . . .	Hermetic
Leads, Flexible. . . . .	3
Maximum length. . . . .	1.525"
Orientation and diameter. . . . .	See <i>Dimensional Outline</i>
Terminal Diagram (See <i>Dimensional Outline</i> ):	



### INDUSTRIAL SERVICE

*Such as in dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and servo-amplifier, and relay-actuating circuits*

### Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	60 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With emitter-to-base reverse biased (DC emitter-to-base volts = 1.5). . . . .	60 max.	volts
With base open (Sustaining voltage) <sup>a</sup> . . . . .	40 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	12 max.	volts
COLLECTOR CURRENT . . . . .	3 max.	amp
EMITTER CURRENT . . . . .	-3.5 max.	amp
BASE CURRENT. . . . .	1.5 max.	amp
TRANSISTOR DISSIPATION: <sup>b</sup>		
At case temperature of 25° C <sup>c</sup> . . . . .	40 max.	watts
At case temperature of 100° C <sup>c</sup> . . . . .	22.9 max.	watts
CASE-TEMPERATURE RANGE: <sup>c</sup>		
Operating and storage . . . . .	-65 to +200	°C
LEAD TEMPERATURE: <sup>d</sup>		
For 10 seconds maximum. . . . .	255 max.	°C

### Characteristics:

*At case temperature of 25° C<sup>c</sup>*

Alpha-Cutoff Frequency ( $f_{ab}$ ) with dc collector-to-base volts = 28, dc collector ma. = 5. . . . .	1.25	Mc
---	------	----



# 2N1768

Collector-to-Base Capacitance ( $C_{ob}$ )			
with dc collector-to-base volts = 40. . . . .	175		$\mu\mu\text{f}$
Thermal Time Constant ( $\tau_1$ ). . . . .	10		msec

## Typical Operation:

*In accompanying typical power-switching circuit at case temperature<sup>c</sup> of 25° C*

DC Supply Voltage ( $B_2$ ). . . . .	12	volts
DC Base-Bias Voltage ( $B_1$ ) . . . . .	-8.5	volts
"On" DC Collector Current . . . . .	750	ma
"Turn-On" Base Current ( $I_{B1}$ ). . . . .	65	ma
"Turn-Off" Base Current ( $I_{B2}$ ) . . . . .	-35	ma
Generator Resistance. . . . .	50	ohms
Switching Time:		
Delay time ( $t_d$ ) . . . . .	0.2	$\mu\text{sec}$
Rise time ( $t_r$ ). . . . .	1	$\mu\text{sec}$
Storage time ( $t_s$ ) . . . . .	0.8	$\mu\text{sec}$
Fall time ( $t_f$ ). . . . .	1.1	$\mu\text{sec}$

- <sup>a</sup> The Collector-to-Emitter Sustaining voltage ( $V_{CE0(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $\alpha_{EM} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).
- <sup>b</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.
- <sup>c</sup> Measured at any point on seating plane of pedestal.
- <sup>d</sup> Measured  $1/16'' \pm 1/32''$  down from case.

## ELECTRICAL CHARACTERISTICS

*Voltage values are given with respect to base and at case temperature<sup>c</sup> of 25° C unless otherwise specified*

	Min.	Max.	
Collector-to-Emitter Voltage:			
With emitter reverse bias			
volts = 1.5, dc collector			
ma. = 0.25. . . . .	$V_{CEX}$	60	- volts
With base open (Sustaining			
voltage), dc collector			
ma. = 100, dc base ma. = 0.	$V_{CE0}^a$	40	- volts
(Base-to-Emitter Voltage for			
dc collector-to-emitter			
volts = 4, dc collector			
ma. = 750 . . . . .	$V_{BE}$	-	2.5 volts
Collector-Cutoff Current	$I_{CBO}$		
for dc collector volts = 30,			
dc emitter ma. = 0, case			
temperature <sup>c</sup> =			
25° C . . . . .		-	15 $\mu\text{a}$
150° C. . . . .		-	750 $\mu\text{a}$
Emitter-Cutoff Current for			
dc emitter volts = 12, dc			
emitter ma. = 0 . . . . .	$I_{EBO}$	-	15 $\mu\text{a}$



DC Current Transfer Ratio for dc collector-to-emitter volts = 4, dc collector ma. = 750 . . . . .	$h_{FE}$	35	100	
DC Collector-to-Emitter Saturation Resistance for dc collector ma. = 750, dc base ma. = 40 . . . . .	$R_S$ $R_T$	-	1	ohm
Thermal Resistance:				
Junction-to-case. . . . .		-	4.375	$^{\circ}\text{C}/\text{watt}$
Junction-to-free air. . . . .		-	175	$^{\circ}\text{C}/\text{watt}$

<sup>a</sup> The Collector-to-Emitter Sustaining Voltage ( $V_{CE(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{\alpha M} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

<sup>c</sup> Measured at any point on seating plane of pedestal.

### OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

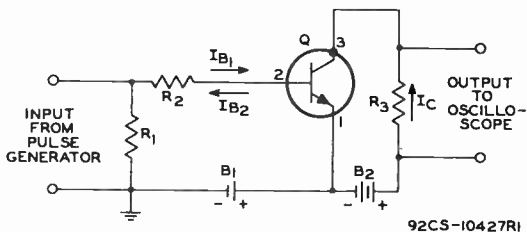
The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the seals of the leads and damage the transistor.

It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.



# 2N1768

## TYPICAL POWER-SWITCHING CIRCUIT



$B_1$ : 8.5 volts

$B_2$ : 12 volts

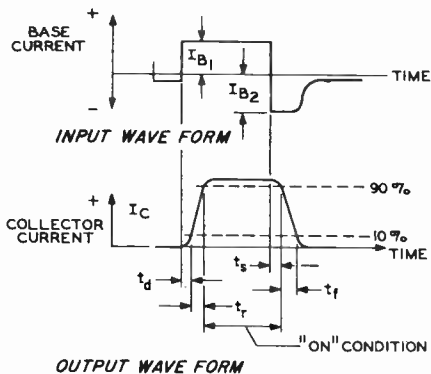
Q: Transistor type 2N1768

$R_1$ : 50 ohms, 1 watt

$R_2$ : 220 ohms, 1 watt

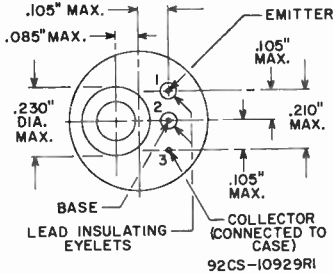
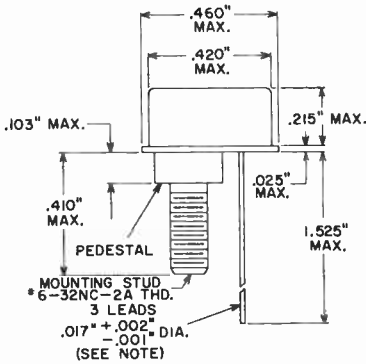
$R_3$ : 15.9 ohms, 2 watts

## ASSOCIATED WAVE FORMS



92CS-10029

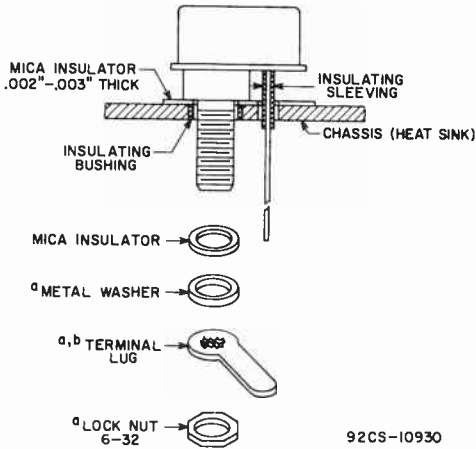
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NOTE: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE BOTTOM OF THE CASE. BETWEEN 0.25" AND THE END OF THE LEAD, A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

# 2N1768

## SUGGESTED MOUNTING ARRANGEMENT

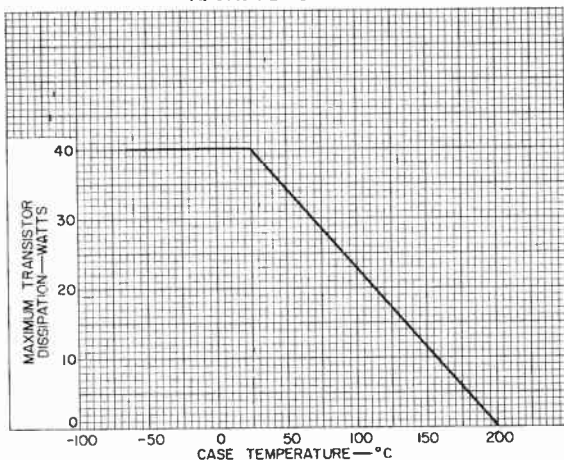


<sup>a</sup> Supplied with each transistor.

<sup>b</sup> Shakeproof Division, Illinois Tool Works,  
Cat. No. 2102-6.

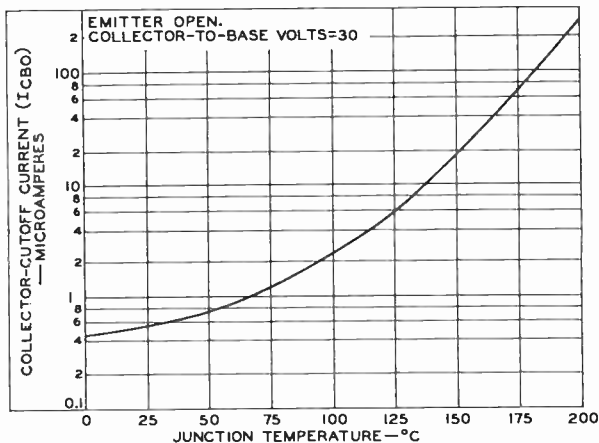


## RATING CHART



92CS-10928

## TYPICAL COLLECTOR-CUTOFF-CURRENT CHARACTERISTIC



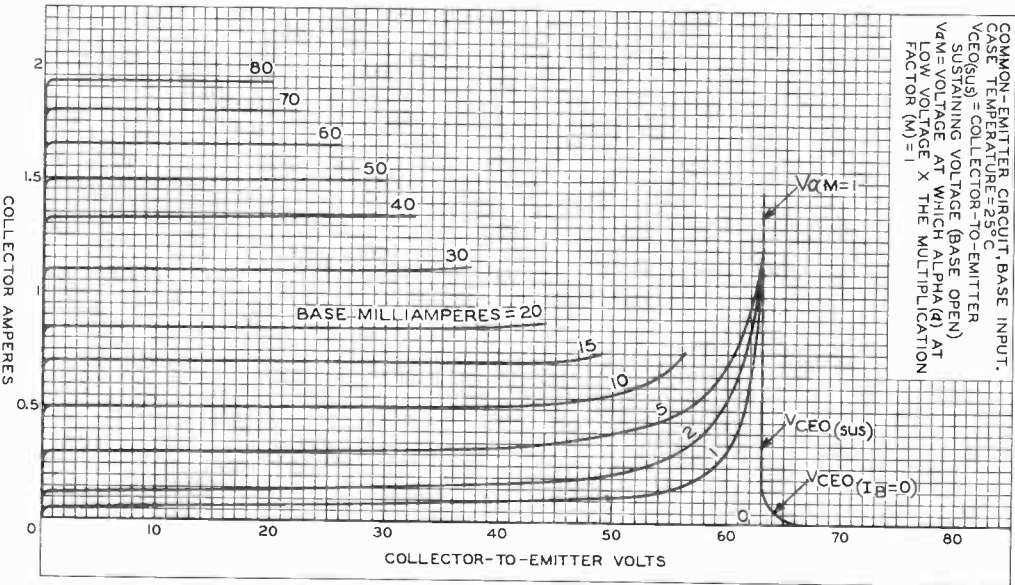
92CS-10882



# 2N1768

## TYPICAL COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT,  
CASE TEMPERATURE = 25°C  
 $V_{CE0}(sus)$  = COLLECTOR-TO-EMITTER  
SUSTAINING VOLTAGE (BASE OPEN)  
 $V_{CE0}(I_B=0)$  = VOLTAGE AT WHICH ALPHA ( $\alpha$ ) AT  
LOW VOLTAGE X THE MULTIPLICATION  
FACTOR ( $M$ ) = 1

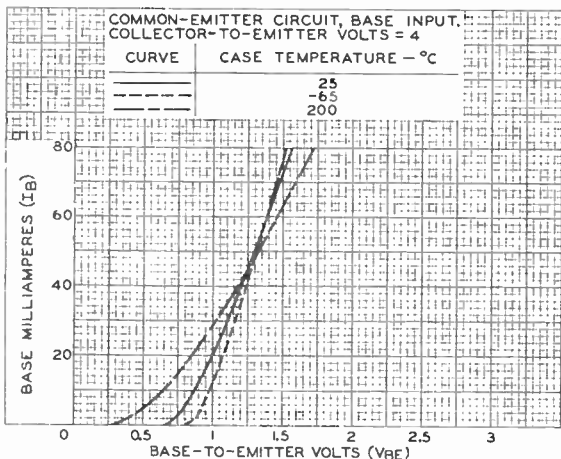


92CM-10445RI

RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division  
Somerville, N. J.

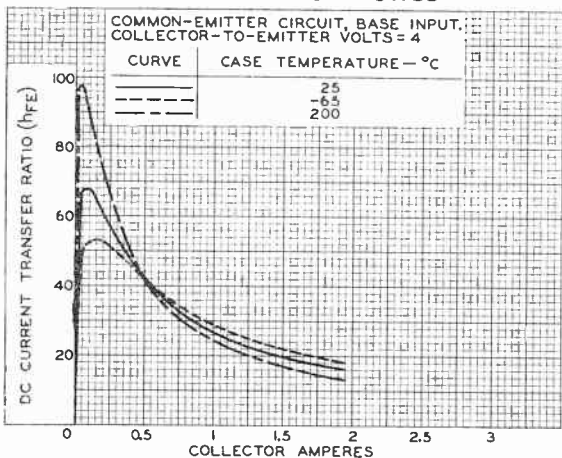


## TYPICAL BASE CHARACTERISTICS



92CS-10443R3

## TYPICAL DC-CURRENT-TRANSFER-RATIO CHARACTERISTICS



92CS-10444R2





## Power Transistor

### SILICON N-P-N DIFFUSED-JUNCTION TYPE For Industrial Applications

The 2N1769 is the same as the 2N1768 except for the following items:

#### INDUSTRIAL SERVICE

Such as is dc-to-dc converter, inverter, chopper, voltage- and current-regulator, dc- and servo-amplifier, and relay-actuating circuits

#### Maximum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	100 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With emitter-to-base reverse biased		
(DC emitter-to-base volts = 1.5). . .	100 max.	volts
With base open (Sustaining voltage) <sup>a</sup> . .	55 max.	volts

#### ELECTRICAL CHARACTERISTICS

		Min.	Max.	
Collector-to-Emitter Voltage:				
With emitter reverse bias				
volts = 1.5, dc collector				
ma. = 0.25. . . . .	$V_{CEX}$	100	-	volts
With base open (Sustaining				
voltage), dc collector				
ma. = 100, dc base				
ma. = 0 . . . . .	$V_{CEO}^a (sus)$	55	-	volts

<sup>a</sup> The Collector-to-Emitter Sustaining Voltage ( $V_{CEO}(sus)$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{CEM} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).





## Transistor

GERMANIUM P-N-P DIFFUSED-JUNCTION MESA TYPE  
 For High-Speed Saturated Switching Applications  
 in Commercial and Military Data-Processing Systems

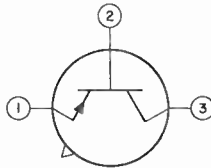
### GENERAL DATA

#### Mechanical:

Dimensions. . . . . See Outline TO-5 in General Section

Terminal Diagram: BOTTOM VIEW

Lead 1 - Emitter  
 Lead 2 - Base



Lead 3 - Collector

### SWITCHING SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values:*

#### COLLECTOR-TO-BASE VOLTAGE:

With emitter open . . . . .  $V_{CBO}$  -18 max. volts

#### COLLECTOR-TO-EMITTER VOLTAGE:

With base open. . . . .  $V_{CEO}$  -6 max. volts

#### EMITTER-TO-BASE VOLTAGE:<sup>a</sup>

With collector open . . . . .  $V_{EB0}$  -2 max. volts

#### COLLECTOR CURRENT . . . . .

$I_C$  -100 max. ma

#### TRANSISTOR DISSIPATION:<sup>b</sup>

At free-air temperature of

25° C or below. . . . . P 150 max. mw

#### EMITTER-TO-BASE DISSIPATION:

With emitter-to-base reverse bias

dc volts = -2, free-air temperature

of 25° C or below . . . . . 25 max. mw

#### FREE-AIR TEMPERATURE RANGE:

Junction (Operating). . . . .  $T_J$  -55 to +85 °C

Storage . . . . .  $T_{STG}$  -55 to +85 °C

#### LEAD TEMPERATURE:<sup>c</sup>

For 10 seconds maximum. . . . .  $T_L$  235 max. °C

<sup>a</sup> This rating may be exceeded and the emitter-to-base junction operated in the breakdown condition provided the emitter-to-base dissipation is limited to 25 milliwatts at 25° C. For free-air temperatures above 25° C, reduce the dissipation.

<sup>b</sup> See accompanying Rating Chart and Transistor-Dissipation Rating Chart in General Section.

<sup>c</sup> Measured 1/16" ± 1/32" along lead, down from seating plane.



# 2N1853

## ELECTRICAL CHARACTERISTICS

Unless otherwise specified, free-air temperature = 25° C  
 Min. Max.

DC Collector-to-Base Breakdown Voltage for dc collector ma. = -0.025, dc emitter current = 0 . . . . .	$BV_{CBO}$	-18	-	volts
DC Collector-to-Emitter Breakdown Voltage for base-to-emitter reverse bias dc volts = -0.15, dc collector ma. = -0.025 . . . . .	$BV_{CEV}$	-18	-	volts
DC Emitter-to-Base Breakdown Voltage for dc emitter ma. = -0.1, dc collector current = 0 . . . . .	$BV_{EBO}$	-2	-	volts
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = -6, dc base ma. = -0.2 . . . . .	$V_{CE(sat)}$	-	-0.2	volt
DC Base-to-Emitter Voltage for dc collector ma. = -6, dc base ma. = -0.2 . . . . .	$V_{BE}$	-	-0.4	volt
DC Collector-Cutoff Current: With dc collector-to-base volts = -15, dc emitter current = 0 . . . . .	$I_{CBO}$	-	-4.2	$\mu$ a
With dc collector-to-base volts = -18, dc emitter current = 0, free-air temperature = 60. . . . .		-	-35	$\mu$ a
DC Emitter-Cutoff Current for dc emitter-to-base volts = -2, dc collector current = 0 . . . . .	$I_{EBO}$	-	-100	$\mu$ a
DC Forward-Current Transfer Ratio: With dc collector-to-emitter volts = -1, dc base ma. = -0.2 . . . . .	$h_{FE}$	30	400	
With dc collector-to-emitter volts = -0.4, dc collector ma. = -6 . . . . .		30	-	
Switching Time: Turn-on time <sup>d</sup> . . . . .	$t_{on}$	-	0.8	$\mu$ sec
Turn-off time <sup>e</sup> . . . . .	$t_{off}$	-	0.9	$\mu$ sec
Storage time <sup>e</sup> . . . . .	$t_s$	-	0.8	$\mu$ sec

<sup>d</sup> See accompanying Turn-On-Time ( $t_{on}$ ) Measurement Circuit.

<sup>e</sup> See accompanying Turn-Off-Time ( $t_{off}$ ) and Storage-Time ( $t_s$ ) Measurement Circuit.

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The flexible leads of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the seating plane provided care is taken to conduct

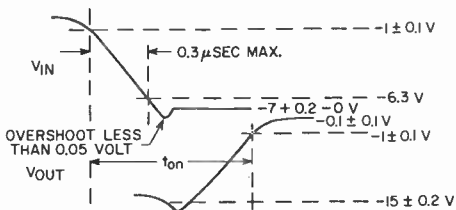
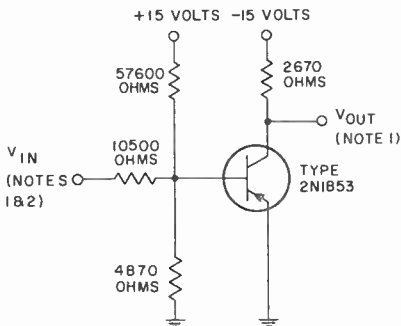




excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the seals of the leads and damage the transistor.

This transistor is intended for use in single-side printed-circuit boards and in conventional wire-in type circuits. If this transistor is used in double-side printed-circuit boards or in printed-circuit boards utilizing eyelets, it may be necessary to use an insulating washer or similar standoff device made of good dielectric material to prevent the solder from shorting the leads to each other or to the board, and to prevent the base from shorting to ground.

### TURN-ON-TIME MEASUREMENT CIRCUIT AND ASSOCIATED WAVE FORMS



92CS-11717

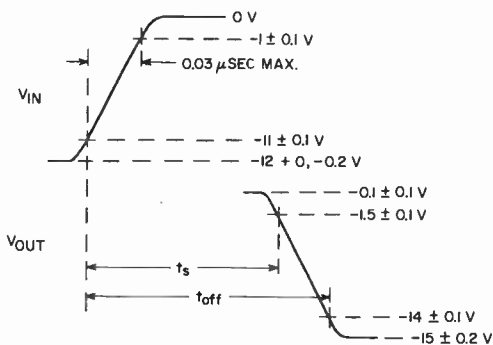
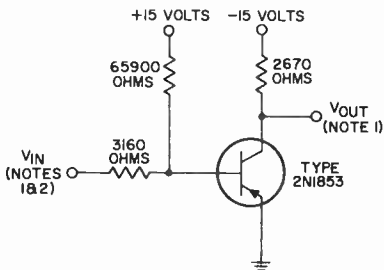
**NOTE 1:** INPUT AND OUTPUT WAVE FORMS ( $V_{IN}$  AND  $V_{OUT}$ ) SHOULD BE MONITORED BY MEANS OF A SAMPLING OSCILLOSCOPE HAVING A RISE TIME OF LESS THAN 15 NANoseconds, A PROBE CAPACITANCE OF NOT MORE THAN 12 PF, AND A SHUNT RESISTANCE OF NOT LESS THAN 10 MEGOHMS.

**NOTE 2:** INPUT VOLTAGE ( $V_{IN}$ ) OBTAINED FROM A MERCURY-RELAY TYPE PULSE GENERATOR HAVING AN OUTPUT IMPEDANCE OF 100 OHMS.



# 2N1853

## TURN-OFF-TIME AND STORAGE-TIME MEASUREMENT CIRCUIT AND ASSOCIATED WAVE FORMS

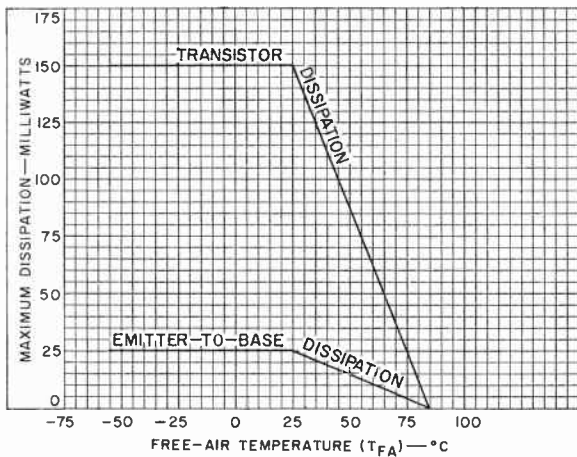


92CS-11718

**NOTE 1:** INPUT AND OUTPUT WAVE FORMS ( $V_{IN}$  AND  $V_{OUT}$ ) SHOULD BE MONITORED BY MEANS OF A SAMPLING OSCILLOSCOPE HAVING A RISE TIME OF LESS THAN 15 NANoseconds, A PROBE CAPACITANCE OF NOT MORE THAN 12 PF, AND A SHUNT RESISTANCE OF NOT LESS THAN 10 MEGOHMS.

**NOTE 2:** INPUT VOLTAGE ( $V_{IN}$ ) OBTAINED FROM A MERCURY-RELAY TYPE PULSE GENERATOR HAVING AN OUTPUT IMPEDANCE OF 100 OHMS.

## RATING CHART



92CS 11714





## Transistor

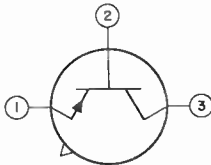
GERMANIUM P-N-P DIFFUSED-JUNCTION MESA TYPE  
 For High-Speed Saturated Switching Applications  
 in Commercial and Military Data-Processing Systems

### GENERAL DATA

#### Mechanical:

Dimensions . . . . . See Outline T0-5 in General Section  
 Terminal Diagram: BOTTOM VIEW

Lead 1 - Emitter  
 Lead 2 - Base



Lead 3 - Collector

### SWITCHING SERVICE

Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE:			
With emitter open . . . . .	$V_{CB0}$	-18 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:			
With base open . . . . .	$V_{CE0}$	-6 max.	volts
EMITTER-TO-BASE VOLTAGE: <sup>a</sup>			
With collector open . . . . .	$V_{EB0}$	-2 max.	volts
COLLECTOR CURRENT . . . . .	$I_C$	-100 max.	ma
TRANSISTOR DISSIPATION: <sup>b</sup>			
At free-air temperature of 25° C or below . . . . .	P	150 max.	mw
EMITTER-TO-BASE DISSIPATION:			
With emitter-to-base reverse bias dc volts = -2, free-air temperature of 25° C or below . . . . .		25 max.	mw
FREE-AIR TEMPERATURE RANGE:			
Junction (Operating) . . . . .	$T_J$	-55 to +85	°C
Storage . . . . .	$T_{STG}$	-55 to +85	°C
LEAD TEMPERATURE: <sup>c</sup>			
For 10 seconds maximum . . . . .	$T_L$	235 max.	°C

<sup>a</sup> This rating may be exceeded and the emitter-to-base junction operated in the breakdown condition provided the emitter-to-base dissipation is limited to 25 milliwatts at 25° C. For free-air temperatures above 25° C, reduce the dissipation.

<sup>b</sup> See accompanying Rating Chart and Transistor-Dissipation Rating Chart in General Section.

<sup>c</sup> Measured 1/16" ± 1/32" along lead, down from seating plane.



# 2N1854

## ELECTRICAL CHARACTERISTICS

Unless otherwise specified, free-air temperature = 25° C

		Min.	Max.	
DC Collector-to-Base Breakdown Voltage for dc collector ma. = -0.025, dc emitter current = 0	$BV_{CBO}$	-18	-	volts
DC Collector-to-Emitter Breakdown Voltage for base-to-emitter reverse bias dc volts = -0.2, dc collector ma. = -0.025 . .	$BV_{CEV}$	-18	-	volts
DC Emitter-to-Base Breakdown Voltage for dc emitter ma. = -0.1, dc collector current = 0	$BV_{EBO}$	-2	-	volts
DC Collector-to-Emitter Latching Voltage <sup>d</sup> for dc collector supply volts = -18, emitter-to-base resistance (ohms) = 1000, load resistance (ohms) = 178 . . .	$V_{CERL}$	-17	-	volts
DC Collector-to-Emitter Saturation Voltage:	$V_{CE(sat)}$			
With dc collector ma. = -20, dc base ma. = -0.66 . . . . .		-	-0.25	volt
With dc collector ma. = -20, dc base ma. = -0.5 . . . . .		-	-0.3	volt
With dc collector ma. = -80, dc base ma. = -2.7, free-air temperature = 55° C . . . . .		-	-0.7	volt
DC Base-to-Emitter Voltage for dc collector ma. = -20, dc base ma. = -0.5 . . . . .	$V_{BE}$	-	-0.8	volt
DC Collector-Cutoff Current:	$I_{CBO}$			
With dc collector-to-base volts = -15, dc emitter current = 0, free-air temperature = 25° C . . . . .		-	-4.2	$\mu a$
65° C . . . . .		-	-40	$\mu a$
DC Emitter-Cutoff Current for dc emitter-to-base volts = -2, dc collector current = 0 . . .	$I_{EBO}$	-	-100	$\mu a$
Output Capacitance for dc collector-to-base volts = -10, dc emitter current = 0 . . . . .	$C_{ob}$	-	12	pf
DC Forward-Current Transfer Ratio:	$h_{cc}$			
With dc collector-to-emitter volts = -0.5, dc collector ma. = -20 . . . . .		40	-	
With dc collector-to-emitter volts = -0.75, dc collector ma. = -100 . . . . .		25	-	
With dc collector-to-emitter volts = -1, dc collector ma. = -50 . . . . .		-	400	



Gain-Bandwidth Product for dc collector-to-emitter volts = -1, dc collector ma. = -10, small-signal short-circuit forward-current transfer ratio = 5 . . . . .

$f_T$  40 - Mc

Charge Storage Time:<sup>e</sup>

$t_{Qs}$

With dc collector ma. = -20,  
turn-on dc base ma. = -1.5.  
With dc collector ma. = -80,  
turn-on dc base ma. = -4.5.

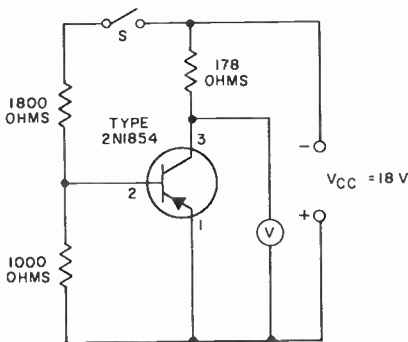
- 60 nsec

- 80 nsec

<sup>d</sup> See accompanying Collector-to-Emitter Latching-Voltage Measurement Circuit.

<sup>e</sup> See accompanying Charge-Storage-Time Measurement Circuit.

## COLLECTOR-TO-EMITTER LATCHING-VOLTAGE MEASUREMENT CIRCUIT



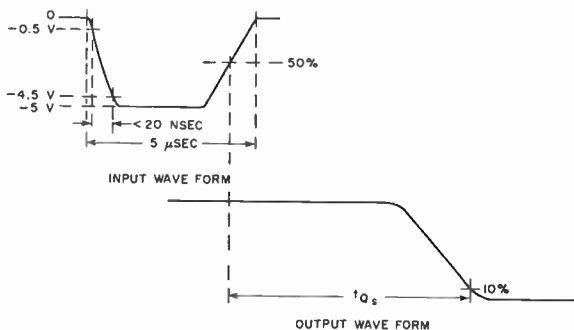
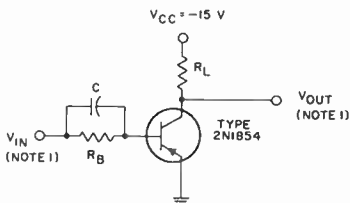
92CS 11715R1

THE TRANSISTOR IS INSERTED IN THE CIRCUIT WITH SWITCH (S) OPEN. THE SWITCH IS THEN CLOSED AND IMMEDIATELY REOPENED. THE RESULTING COLLECTOR-TO-EMITTER VOLTAGE IS THE "LATCHING" VOLTAGE,  $V_{CERL}$ .



# 2N1854

## CHARGE-STORAGE-TIME MEASUREMENT CIRCUIT AND ASSOCIATED WAVE FORMS



92CS 11720

For dc collector ma. = -20

C: 150 pf

$I_{B1}$ : Turn-on dc base ma. = -1.5

$R_B$ : 3300 ohms

$R_L$ : 750 ohms

For dc collector ma. = -80

C: 510 pf

$I_{B1}$ : Turn-on dc base ma. = -4.5

$R_B$ : 1100 ohms

$R_L$ : 189 ohms

NOTE 1: INPUT AND OUTPUT WAVE FORMS ( $V_{IN}$  AND  $V_{OUT}$ ) SHOULD BE MONITORED BY MEANS OF A SAMPLING OSCILLOSCOPE HAVING A RISE TIME OF LESS THAN 15 NANoseconds, A PROBE CAPACITANCE OF NOT MORE THAN 12 PF, AND A SHUNT RESISTANCE OF NOT LESS THAN 10 MEGOHMS.

### OPERATING CONSIDERATIONS

and

### RATING CHART

shown under type 2N1853 also apply to the 2N1854





## Power Transistor

GERMANIUM, P-N-P, DIFFUSED-COLLECTOR, GRADED-BASE, DRIFT-FIELD TYPE

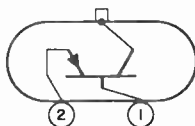
For Industrial and Consumer-Product Applications

### GENERAL DATA

#### Mechanical:

Operating Position . . . . .	Any
Maximum Seated Length . . . . .	0.440"
Maximum Length of Mounting Flange . . . . .	1.562"
Maximum Width of Mounting Flange . . . . .	1.031"
Case . . . . .	Metal
Mounting Flange . . . . .	Metal
Seals . . . . .	Hermetic
Socket . . . . .	Loranger Mfg. Corp. No.2149, or equivalent
Terminal Diagram (See <i>Dimensional Outline</i> ):	

Pin 1 - Base  
Pin 2 - Emitter



MOUNTING FLANGE--  
Collector,  
Case

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

*In such applications as high-power, high-speed switches in dc-to-dc converters, inverters, and computers for data-processing equipment, as ultrasonic oscillators, and as large-signal, wide-band linear amplifiers*

COLLECTOR-TO-BASE VOLTAGE . . . . .	-60 max. volts
COLLECTOR-TO-EMITTER VOLTAGE:	
With base open . . . . .	-40 max. volts
EMITTER-TO-BASE VOLTAGE . . . . .	-1 max. volt
COLLECTOR CURRENT . . . . .	-10 max. amp
BASE CURRENT . . . . .	-3 max. amp
TRANSISTOR DISSIPATION:	
For mounting-flange temperatures <sup>a</sup>	
up to 25° C . . . . .	50 max. watts
For mounting-flange temperatures <sup>a</sup>	
above 25° C . . . . .	See Rating Chart
MOUNTING-FLANGE TEMPERATURE <sup>a</sup> RANGE:	
Operating and storage . . . . .	-55 to +100 °C
PIN TEMPERATURE: <sup>b</sup>	
For 10 seconds maximum . . . . .	255 max. °C

<sup>a</sup> Measured at center of seating surface.

<sup>b</sup> Measured 1/16" ± 1/32" down from plane of seating surface.



# 2N1905

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base unless otherwise specified. Mounting-flange temperature<sup>a</sup> of 25° C.

Min. Typical Max.

DC Collector Breakdown Voltage for dc collector ma. = -10, emitter current = 0 . . .	$BV_{CBO}$	-60	-80	-	volts
DC Collector-to-Emitter Breakdown Voltage for dc collector ma. = -100, base current = 0 . . . .	$BV_{CEO}$	-40	-55	-	volts
DC Emitter Breakdown Voltage for dc emitter ma. = -5, collector current = 0 . . . . .	$BV_{EBO}$	-1	-2	-	volts
DC Base-to-Emitter Voltage for dc collector-to-emitter volts = -2, dc collector ma. = -1000 . . . . .	$V_{BE}$	-	-0.38	-0.5	volt
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = -1000, dc base ma. = -50 . . . . .	$V_{CE(sat)}$	-	-0.3	-1	volt
DC Collector-Cutoff Current for dc collector volts = -40, emitter current = 0 . . .	$I_{CBO}$	-	-150	-500	$\mu a$
DC Collector-Cutoff Saturation Current for dc collector volts = -0.5, emitter current = 0 . . . . .	$I_{CBO(sat)}$	-	-65	-100	$\mu a$
DC Emitter-Cutoff Current for dc emitter volts = -0.5, collector current = 0 . . . . .	$I_{EBO}$	-	-1	-	ma
DC Current Transfer Ratio for dc collector-to-emitter volts = -2, dc collector ma. = -1000 .	$h_{FE}$	50	90	150	
Forward Current-Transfer-Ratio Cutoff Frequency for dc collector-to-emitter volts = -5, dc collector ma. = -500. . .	$f_{hfe}$	-	75	-	kc
Gain-Bandwidth Product for dc collector-to-emitter volts = -5, dc collector ma. = -500. . . . .	$f_T$	5	7.5	-	Mc



DC Forward Conductance  
 ( $I_C/V_{BE}$ ) for dc col-  
 lector-to-emitter  
 volts = -2, dc col-  
 lector ma. = -1000. . .

$G_{FE}$	2	4	-	mhos
----------	---	---	---	------

Thermal Resistance:

Junction-to-mounting

flange. . . . .	$R_T$	-	-	1.5	$^{\circ}C/watt$
-----------------	-------	---	---	-----	------------------

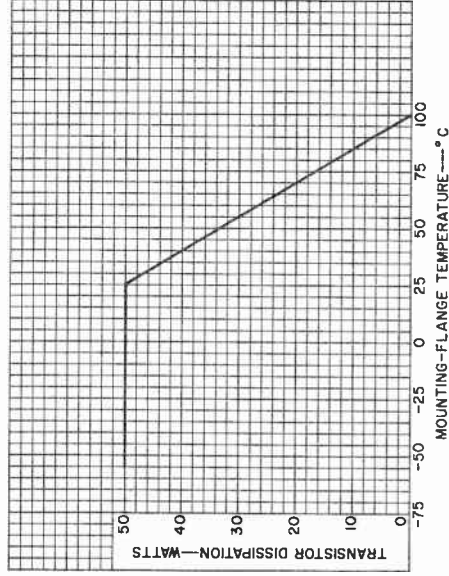
<sup>a</sup> Measured at center of seating surface.

**OPERATING CONSIDERATIONS,  
 DIMENSIONAL OUTLINE,  
 and  
 SUGGESTED MOUNTING ARRANGEMENT**  
 shown under type 2N1906 also apply to the 2N1905



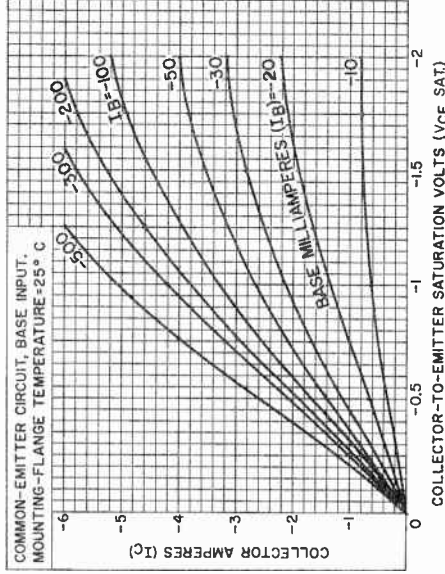
# 2N1905

## RATING CHART



92CS-10991

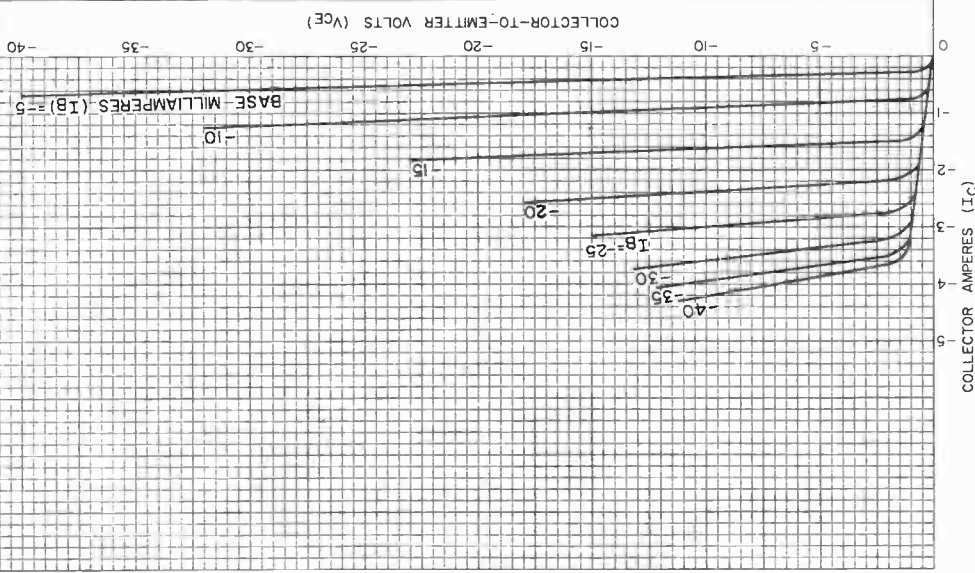
## TYPICAL COLLECTOR-TO-EMITTER SATURATION-VOLTAGE CHARACTERISTICS



92CS-10997

## TYPICAL COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT  
MOUNTING-FLANGE TEMPERATURE = 25° C



92CM-10999RI

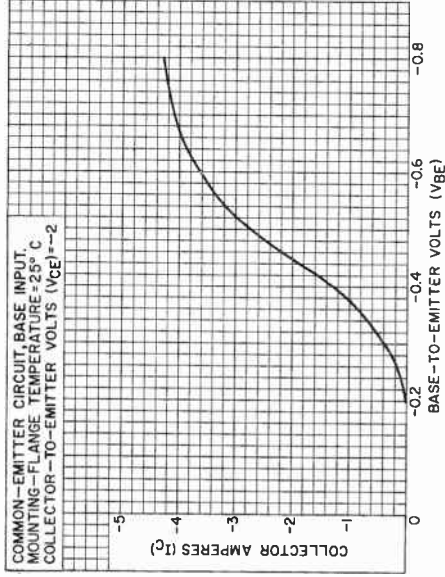


RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division

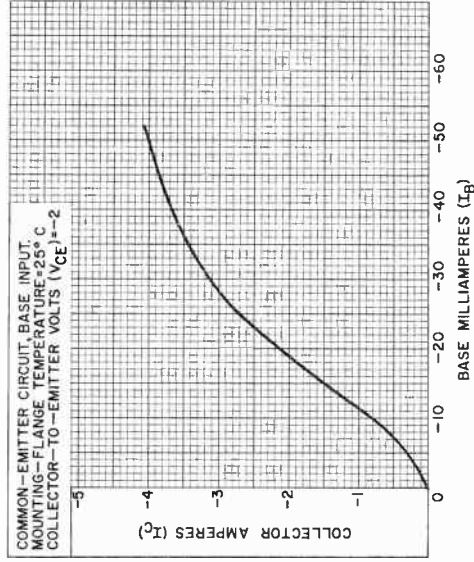
DATA 3  
6-61

# 2N1905

## TYPICAL CHARACTERISTICS



92CS-10995



92CS-10995

## Power Transistor

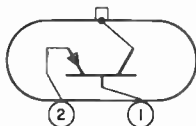
GERMANIUM, P-N-P, DIFFUSED-COLLECTOR,  
GRADED-BASE, DRIFT-FIELD TYPE  
For Industrial and Consumer-Product Applications

### GENERAL DATA

#### Mechanical:

Operating Position . . . . .	Any
Maximum Seated Length . . . . .	0.440"
Maximum Length of Mounting Flange . . . . .	1.562"
Maximum Width of Mounting Flange . . . . .	1.031"
Case . . . . .	Metal
Mounting Flange . . . . .	Metal
Seals . . . . .	Hermetic
Socket . . . . .	Loranger Mfg. Corp. No.2149, or equivalent
Terminal Diagram (See <i>Dimensional Outline</i> ):	

Pin 1 - Base  
Pin 2 - Emitter



MOUNTING FLANGE -  
Collector,  
Case

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

*In such applications as high-power, high-speed switches  
in dc-to-dc converters, inverters, and computers for  
data-processing equipment, as ultrasonic oscillators,  
and as large-signal, wide-band linear amplifiers*

COLLECTOR-TO-BASE VOLTAGE . . . . .	-100 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With base open. . . . .	-40 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-1 max.	volt
COLLECTOR CURRENT . . . . .	-10 max.	amp
BASE CURRENT . . . . .	-3 max.	amp
TRANSISTOR DISSIPATION:		
For mounting-flange temperatures <sup>a</sup>		
up to 25° C . . . . .	50 max.	watts
For mounting-flange temperatures <sup>a</sup>		
above 25° C . . . . .	See Rating Chart	
MOUNTING-FLANGE TEMPERATURE <sup>a</sup> RANGE:		
Operating and storage . . . . .	-55 to +100	°C
PIN TEMPERATURE: <sup>b</sup>		
For 10 seconds maximum. . . . .	255 max.	°C

#### Typical Operation:

*In accompanying typical "on-off" power switching  
circuit at mounting-flange temperature<sup>a</sup> of 25° C*

DC Supply Voltage ( $V_{CC}$ ) . . . . .	5	12.5	12.5	volts
"On" Collector Current . . . . .	-1	-2.5	-5	amp
"Turn-On" Base Current ( $I_{B1}$ ) . . . . .	-	-0.25	-0.25	amp
"Turn-Off" Base Current ( $I_{B2}$ ) . . . . .	-	0.25	0.25	amp



# 2N1906

Pulse-Generator Open-Circuit Voltage (E) . . . . .	2	-	-	volts
Base-Bias Resistor ( $R_1$ ) . . . . .	75	5	5	ohms
"Speed-Up" Capacitor ( $C_1$ ) . . . . .	0.1	-	-	$\mu$ f
Load Resistor ( $R_2$ ) . . . . .	5	5	2.5	ohms
Generator Impedance . . . . .	5	5	5	ohms
Switching Time:				
Delay time ( $t_d$ ) . . . . .	0.1	0.1	0.1	$\mu$ sec
Rise time ( $t_r$ ) . . . . .	0.1	0.4	0.9	$\mu$ sec
Storage time ( $t_s$ ) . . . . .	1	7	7	$\mu$ sec
Fall time ( $t_f$ ) . . . . .	0.6	1	2	$\mu$ sec

<sup>a</sup> Measured at center of seating surface.

<sup>b</sup> Measured  $1/16" \pm 1/32"$  down from plane of seating surface.

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base unless otherwise specified. Mounting-flange temperature<sup>a</sup> of 25°C.

Min. Typical Max.

DC Collector Breakdown Voltage for dc collector ma. = -10, emitter current = 0 . . . . .	$BV_{CBO}$	-100	-130	-	volts
DC Collector-to-Emitter Breakdown Voltage for dc collector ma. = -100, base current = 0 . . . . .	$BV_{CEO}$	-40	-55	-	volts
DC Emitter Breakdown Voltage for dc emitter ma. = -5, collector current = 0 . . . . .	$BV_{EBO}$	-1	-2	-	volts
DC Base-to-Emitter Voltage for dc collector-to-emitter volts = -2, dc collector ma. = -5000 . . . . .	$V_{BE}$	-	-0.6	-0.9	volt
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = -5000, dc base ma. = -250 . . . . .	$V_{CE(sat)}$	-	-0.75	-1	volt
DC Collector-Cutoff Current for dc collector volts = -40, emitter current = 0 . . . . .	$I_{CBO}$	-	-150	-500	$\mu$ a
DC Collector-Cutoff Saturation Current for dc collector volts = -0.5, emitter current = 0 . . . . .	$I_{CBO(sat)}$	-	-65	-100	$\mu$ a
DC Emitter-Cutoff Current for dc emitter volts = -0.5, collector current = 0 . . . . .	$I_{EBO}$	-	-1	-	ma





DC Current Transfer Ratio for dc collector-to-emitter volts = -2, dc collector ma. = -5000. . .	$h_{FE}$	75	125	200	
Forward Current-Transfer-Ratio Cutoff Frequency for dc collector-to-emitter volts = -5, dc collector ma. = -500.	$f_{hfe}$	-	75	-	kc
Gain-Bandwidth Product for dc collector-to-emitter volts = -5, dc collector ma. = -500.	$f_T$	5	7.5	-	Mc
DC Forward Conductance ( $I_C/V_{BE}$ ) for dc collector-to-emitter volts = -2, dc collector ma. = -5000. . .	$G_{FE}$	5.5	8.3	-	mhos
Thermal Resistance: Junction-to-mounting flange. . . . .	$R_T$	-	-	1.5	$^{\circ}\text{C}/\text{watt}$

<sup>a</sup> Measured at center of seating surface.

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

This transistor utilizes the Loranger Mfg. Corp. socket No.2149, or equivalent. Electrical connection can also be made to the base and emitter pins by soldering directly to the pins. Soldering of connections to the pins may be made close to the pin seals provided care is taken to conduct excessive heat away from the pin seal, otherwise the heat of the soldering operation will crack the glass seals of the pins and damage the transistor.

Under no circumstances should the mounting flange be soldered to the heat sink because the heat of the soldering operation will permanently damage the transistor.

It is important that the mounting flange which serves as the collector terminal be securely fastened to a heat sink. Depending on the application, the chassis (heat sink) may be connected either to the positive or negative terminal of the voltage supply.

In applications where the chassis is connected to the negative terminal of the voltage supply, it will be necessary to use an anodized-aluminum insulator having high thermal conductivity, or a 0.002" mica insulator between the mounting flange and the chassis. An aluminum washer should be drilled or punched to provide the two mounting holes, and the clearance holes for the emitter and base pins. The burrs should then



# 2N1906

be removed from the washer and the washer finally anodized. To insure that the anodized insulating layer is not destroyed during mounting, it will also be necessary to remove the burrs from the holes in the chassis. Furthermore, to prevent a short circuit between the mounting bolt and the chassis, it is important that an insulating washer be used between the bolt and the chassis (See *Suggested Mounting Arrangement*).

It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.

To prevent damage to the transistor by thermal runaway, an external resistance may be placed in the emitter or collector circuit. The minimum value of this resistance may be obtained from the following equation:

$$R_{min.} = \frac{E^2}{4 \left( P_o + \frac{25}{K} \right)}$$

where:

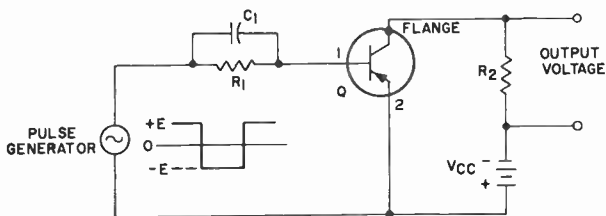
E = DC collector supply voltage (Volts)

P<sub>o</sub> = Collector-to-emitter voltage x collector current at desired operating point (Watts)

K = Thermal resistance — transistor and heat sink (°C/watt)



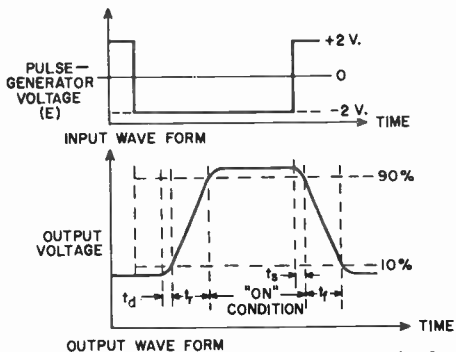
## TYPICAL "ON-OFF" POWER SWITCHING CIRCUIT



92CS-11009R2

Q: Transistor type 2N1906

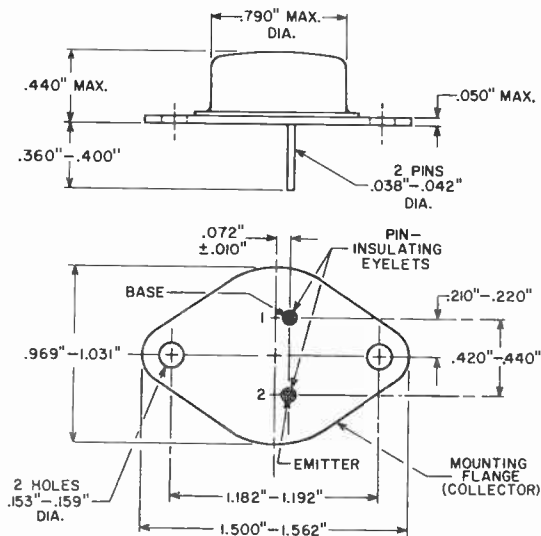
## ASSOCIATED WAVE FORMS



92CS-11011R1

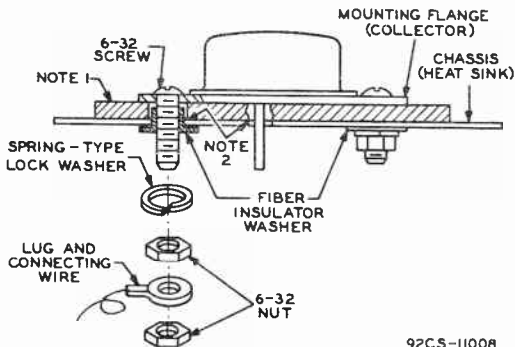


# 2N1906



92CS-11000RI

## SUGGESTED MOUNTING ARRANGEMENT



92CS-11008

NOTE 1: 0.002" MICA INSULATOR OR ANODIZED ALUMINUM INSULATOR (DRILLED OR PUNCHED WITH BURRS REMOVED).

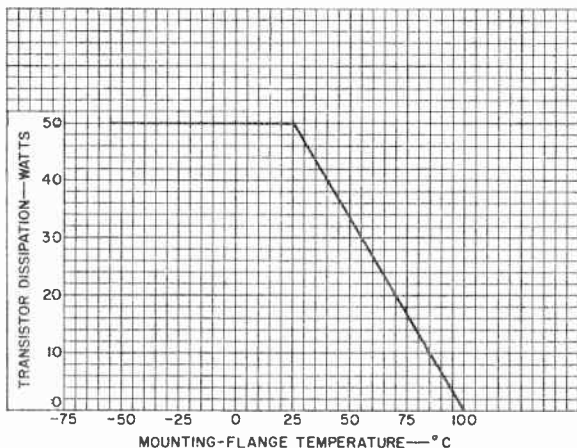
NOTE 2: REMOVE BURRS FROM CHASSIS HOLES.

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Somerville, N. J.

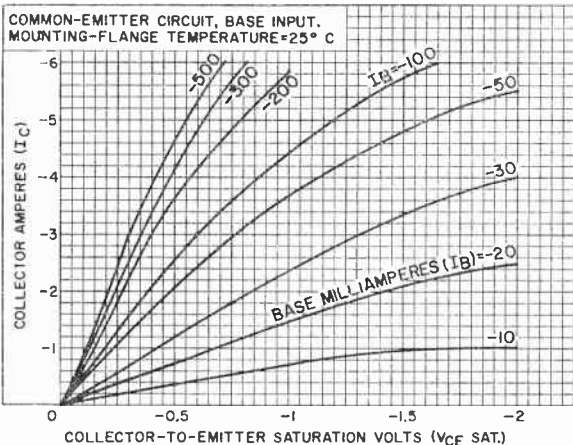


## RATING CHART



92CS-1099I

## TYPICAL COLLECTOR-TO-EMITTER SATURATION-VOLTAGE CHARACTERISTICS



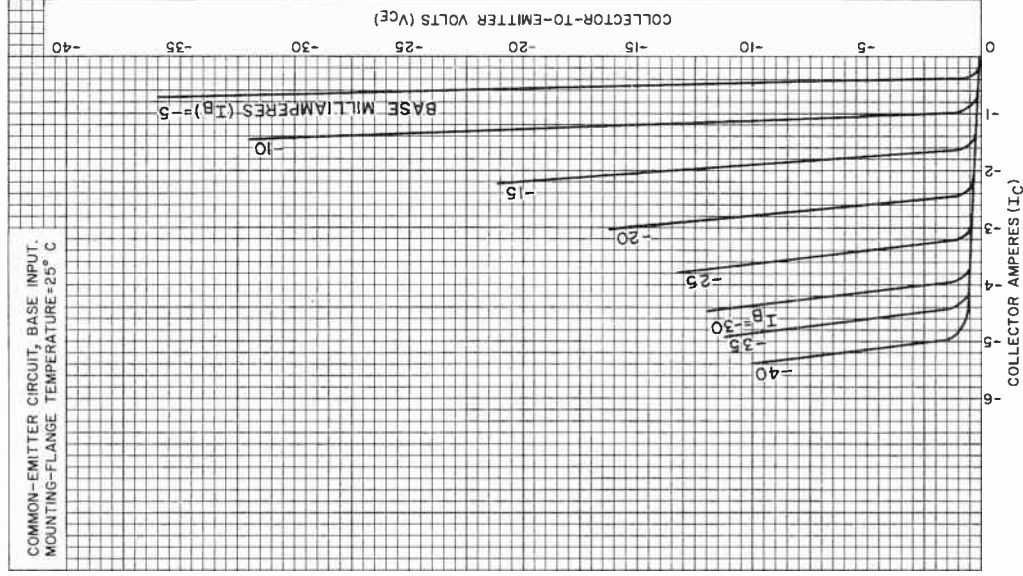
92CS-1099B



# 2N1906

## TYPICAL COLLECTOR CHARACTERISTICS

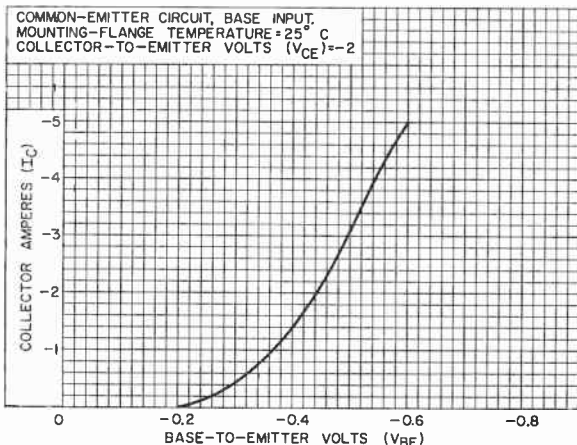
COMMON-EMITTER CIRCUIT, BASE INPUT.  
MOUNTING-FLANGE TEMPERATURE = 25° C



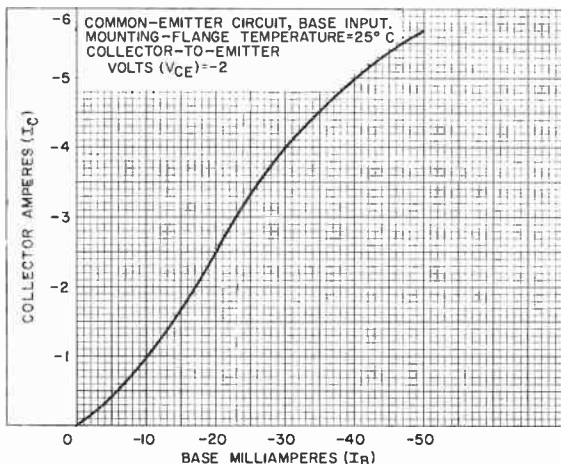
92CM-10996R1

**RCA**  
RADIO CORPORATION OF AMERICA  
Semiconductor & Materials Division  
Somerville, N. J.

## TYPICAL CHARACTERISTICS



92CS-10994



92CS-10992







## Power Transistor

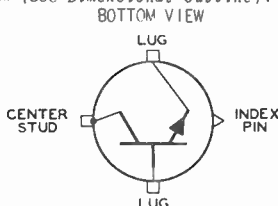
**SILICON N-P-N DIFFUSED-JUNCTION TYPE**  
**For Power Switching and Amplifier Service**  
**in Industrial and Military Applications**

### GENERAL DATA

#### Mechanical:

Operating Position . . . . .	Any
Maximum Seated Length . . . . .	0.520"
Maximum Diameter . . . . .	1.250"
Dimensional Outline . . . . .	JEDEC No. TO-36
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic

Terminal Diagram (See *Dimensional Outline*):



### INDUSTRIAL SERVICE

*Such as dc-to-dc converter, inverter, chopper, relay-control, oscillator, regulator, pulse-amplifier, and class A and class B push-pull-amplifier circuits*

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	100 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With base open (Sustaining voltage) <sup>a</sup> . . . . .	50 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	10 max.	volts
COLLECTOR CURRENT . . . . .	10 max.	amp
EMITTER CURRENT . . . . .	-13 max.	amp
BASE CURRENT . . . . .	6 max.	amp
TRANSISTOR DISSIPATION: <sup>b</sup>		
At case temperature <sup>c</sup> of 25° C or below . . . . .	150 max.	watts
At case temperatures <sup>c</sup> above 25° C . . . . .	See Rating Chart	
CASE-TEMPERATURE RANGE: <sup>c</sup>		
Operating and storage . . . . .	-65 to +200	°C
LUG TEMPERATURE: <sup>d</sup>		
For 10 seconds maximum . . . . .	235 max.	°C

#### Characteristics:

*At case temperature of 25° C*

Forward Current-Transfer-Ratio		
Cutoff-Frequency ( $f_{ae}$ ) . . . . .	25	kc



# 2N2015

Collector-to-Base Capacitance ( $C_{ob}$ )			
with dc collector-to-base volts = 40. . .	400		$\mu\text{mf}$
Thermal Time Constant ( $\tau_f$ ). . . . .	30		msec

## Typical Operation:

*In accompanying pulse-response test circuit at case temperature<sup>c</sup> of 25° C*

Collector Supply Voltage ( $V_{CC}$ ). . . . .	24	volts
DC Base-Bias Voltage ( $V_{BB}$ ). . . . .	-6	volts
"On" DC Collector Current . . . . .	10	amp
"Turn-On" Base Current ( $I_{B1}$ ). . . . .	2	amp
Base Resistance ( $R_{B1}$ ) . . . . .	10	ohms
Base Resistance ( $R_{B2}$ ) . . . . .	10	ohms
Collector Resistance ( $R_C$ ) . . . . .	2	ohms

### Switching Time:

"Turn-on" time [Relay time ( $t_d$ ) + rise time ( $t_r$ )] . . . . .	4	$\mu\text{sec}$
"Turn-off" time [Storage time ( $t_s$ ) + fall time ( $t_f$ )] . . . . .	7	$\mu\text{sec}$

<sup>a</sup> The collector-to-emitter Sustaining Voltage ( $V_{CE0(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $\alpha_{eff} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

<sup>b</sup> See accompanying Rating Chart and also Transistor-Dissipation Rating Chart in General Section.

<sup>c</sup> Measured at intersection of seating surface with mounting stud.

<sup>d</sup> Measured 1/16"  $\pm$  1/32" down from seating surface.

## ELECTRICAL CHARACTERISTICS

*Voltage values are given with respect to base and at case temperature<sup>c</sup> of 25° C unless otherwise specified*

*Min. Max.*

### DC Collector-to-Emitter Voltage:

With emitter reverse-bias volts = 1.5, dc collector ma. = 2 . . . . . $V_{CEX}$	-	100	volts
With base open (Sustaining voltage), dc collector ma. = 200, dc base ma. = 0. . . . . $V_{CE0}^a$ ( $sus$ )	-	50	volts

### DC Base-to-Emitter Voltage for dc collector-to-emitter volts

= 4, dc collector amperes = 5 . . . . . $V_{BE}$ $I_{CBO}$	-	2.2	volts
---	---	-----	-------

### DC Collector-Cutoff Current for dc collector volts = 30, dc emitter ma. = 0, case temperature =

25° C . . . . .	-	50	$\mu\text{a}$
150° C. . . . .	-	2	ma

### DC Emitter-Cutoff Current for dc emitter volts = 10, dc collector ma. = 0 . . . . . $I_{EBO}$

	-	50	$\mu\text{a}$
--	---	----	---------------



DC Forward-Current Transfer Ratio	$h_{FE}$		
for dc collector-to-emitter			
volts = 4, dc collector amperes =			
5 . . . . .		15	50
10 . . . . .		7.5	-
Collector-to-Emitter Saturation			
Resistance for dc collector			
amperes = 5, dc base amperes			
= 0.5 . . . . .	$R_S$	-	0.25 ohm
Thermal Resistance:			
Junction-to-case . . . . .	$R_T$	-	1.17 °C/watt

<sup>a</sup> The Collector-to-Emitter Sustaining Voltage ( $V_{CE0(sus)}$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{AM} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

<sup>c</sup> Measured at intersection of seating surface with mounting stud.

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

Electrical connection can be made to the base and emitter lugs by means of clips or by soldering directly to the lugs. When soldering connections are made to the lugs, care should be taken to conduct excessive heat away from the lug seals, otherwise the heat of the soldering operation will crack the glass seals of the lugs and damage the transistor.

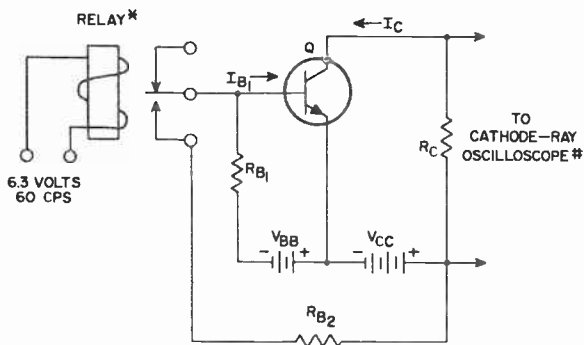
This transistor is provided with a single-ended stud for mounting to a heat sink and for electrical connection to the collector. (See accompanying *Suggested Mounting Arrangement*). Electrical connection to the base and to the emitter is made to their respective lugs.

It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.



# 2N2015

## PULSE-RESPONSE TEST CIRCUIT



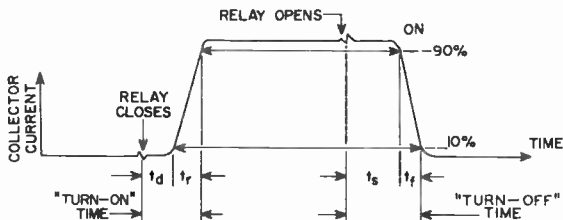
\*C.P. CLARE TYPE HGP-1028  
OR EQUIVALENT

# TEKTRONIX TYPE 545  
OR EQUIVALENT

92CS-11125R1

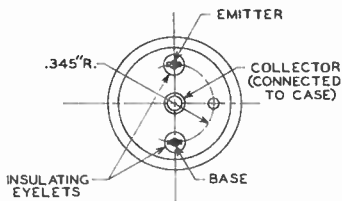
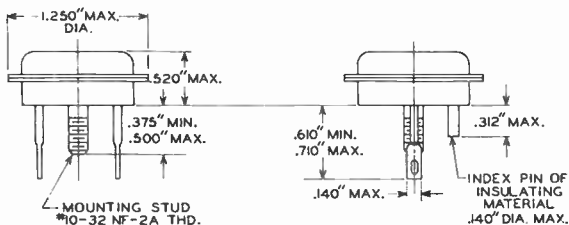
Q: Transistor type 2N2015

## ASSOCIATED WAVE FORM



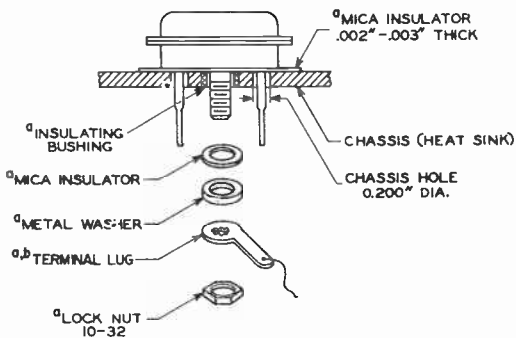
92CS-11126R1

JEDEC No. T0-36



92CM-10612RI

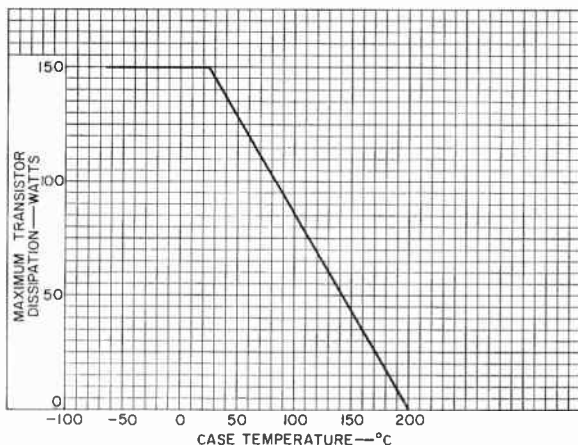
## SUGGESTED MOUNTING ARRANGEMENT



92CS-11133

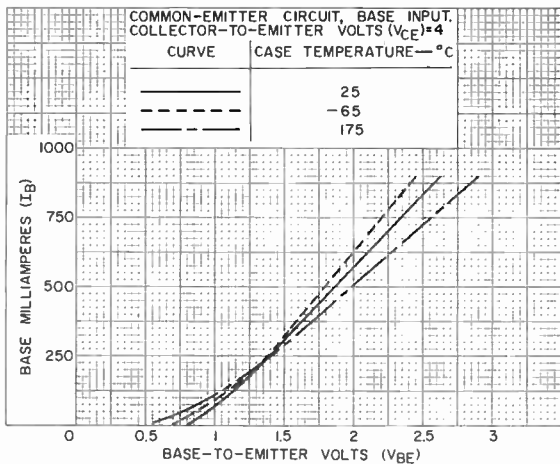
<sup>a</sup> SUPPLIED WITH EACH TRANSISTOR.<sup>b</sup> SHAKEPROOF DIVISION, ILLINOIS TOOL WORKS, CATALOG No. 2102-6.

## RATING CHART



92CS-11089

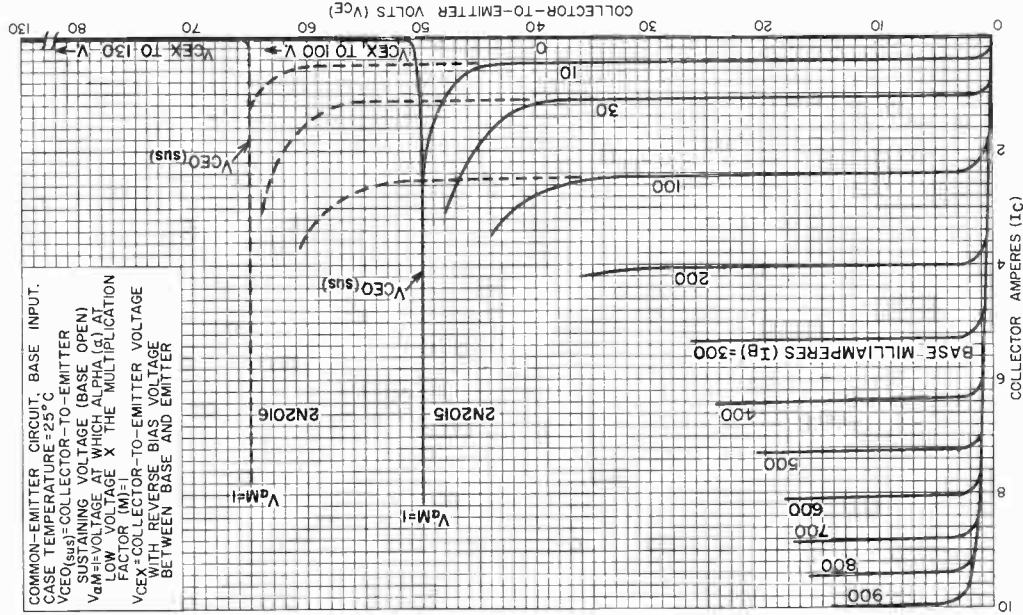
## TYPICAL BASE CHARACTERISTICS



92CS-11093

## TYPICAL COLLECTOR CHARACTERISTICS

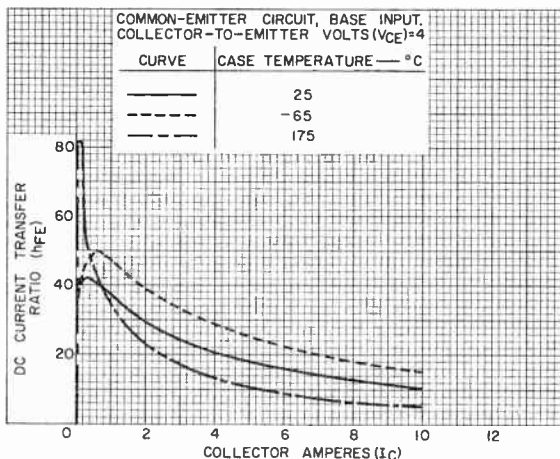
COMMON-EMITTER CIRCUIT, BASE INPUT.  
CASE TEMPERATURE = 25°C  
 $V_{CE0(sus)}$  = COLLECTOR-TO-EMITTER  
SUSTAINING VOLTAGE (BASE OPEN)  
 $V_{dM} = I_C$  VOLTAGE AT WHICH ALPHA ( $\alpha$ ) AT  
LOW VOLTAGE X THE MULTIPLICATION  
FACTOR ( $M$ ) = 1  
 $V_{CEX}$  = COLLECTOR-TO-EMITTER VOLTAGE  
WITH REVERSE BIAS VOLTAGE  
BETWEEN BASE AND EMITTER



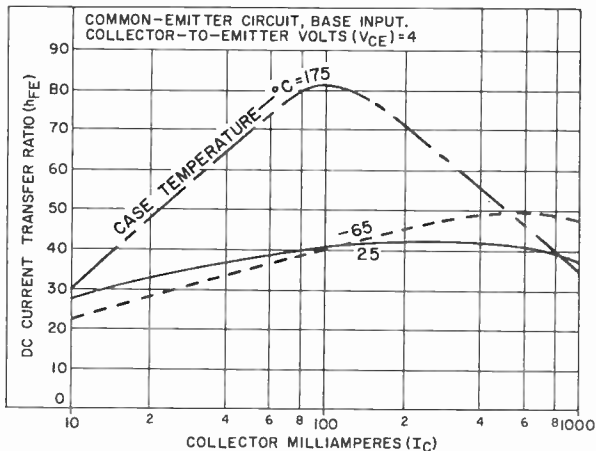
92CM-11092RI



## TYPICAL DC-CURRENT-TRANSFER-RATIO CHARACTERISTICS



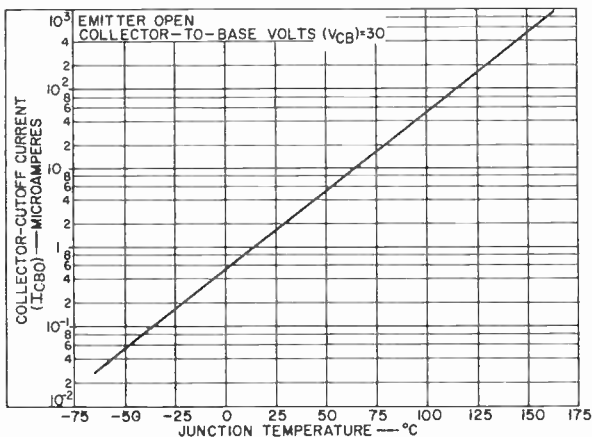
92CS-11090



92CS-11095



## TYPICAL COLLECTOR-CUTOFF-CURRENT CHARACTERISTIC



92CS-11094





## Power Transistor

SILICON N-P-N DIFFUSED-JUNCTION TYPE  
 For Power Switching and Amplifier Service  
 in Industrial and Military Applications

The 2N2016 is the same as the 2N2015 except for the following items:

### INDUSTRIAL SERVICE

Such as in dc-to-dc converter, inverter, chopper, relay-control, oscillator, regulator, pulse-amplifier, and class A and class B push-pull-amplifier circuits

Maximum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	130 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With base open (Sustaining voltage) <sup>a</sup> . . . . .	65 max.	volts

### ELECTRICAL CHARACTERISTICS

	Min.	Max.	
DC Collector-to-Emitter Voltage:			
With emitter reverse-bias			
volts = 1.5, dc collector			
ma. = 2 . . . . .	$V_{CEX}$	-	130 volts
With base open (Sustaining			
voltage), dc collector			
ma. = 200, dc base			
current = 0 . . . . .	$V_{CEO}^a$	(sus)-	65 volts

<sup>a</sup> The Collector-to-Emitter Sustaining voltage ( $V_{CEO}(sus)$ ) with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{CEM} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).





## Transistor

### SILICON N-P-N TRIPLE-DIFFUSED-JUNCTION PLANAR TYPE

For Industrial and Military Applications

The 2N2102 is Unilaterally Interchangeable with Type 2N1613

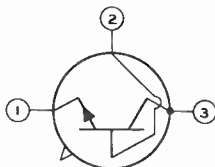
#### GENERAL DATA

##### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter . . . . .	0.370"
Dimensional Outline . . . . .	JEDEC No. TO-5
Case . . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter

Lead 2 - Base



Lead 3 - Collector,  
Case

#### INDUSTRIAL SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values:*

##### COLLECTOR-TO-BASE VOLTAGE:

With emitter open . . . . . 120 max. volts

##### COLLECTOR-TO-EMITTER VOLTAGE:

With external resistance (ohms)  $\leq 10$

    between base and emitter . . . . . 80 max. volts

With base open . . . . . 65 max. volts

##### EMITTER-TO-BASE VOLTAGE:

With collector open . . . . . 7 max. volts

##### COLLECTOR CURRENT:

. . . . . 1 max. amp

##### TRANSISTOR DISSIPATION:<sup>a</sup>

At case temperature<sup>b</sup> of 25°C or below . . . . . 5 max. watts

At free-air temperature of 25°C or below . . . . . 1 max. watt

##### TEMPERATURE RANGE:

Storage . . . . . -65 to +300 °C

Operating (Junction) . . . . . -65 to +200 °C

##### LEAD TEMPERATURE:<sup>c</sup>

For 10 seconds maximum . . . . . 300 max. °C

<sup>a</sup> See accompanying Rating Chart.

<sup>b</sup> Measured at center of seating plane.

<sup>c</sup> Measured 1/16"  $\pm$  1/32" down from seating plane.



# 2N2102

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and at case temperature<sup>b</sup> of 25° C unless otherwise specified

		Min.	Max.	
DC Collector Breakdown Voltage for dc collector ma. = 0.1, dc emitter ma. = 0 . . . . .	$BV_{CBO}$	120	-	volts
DC Emitter Breakdown Voltage for dc collector ma. = 0, dc emitter ma. = 0.1 . . . . .	$BV_{EBO}$	7	-	volts
DC Collector-to-Emitter Reach-Through Voltage for dc emitter volts = 1.5, dc collector ma. = 0.1 . . . . .	$V_{RT}$	120	-	volts
DC Collector-to-Emitter Sustaining Voltage for dc collector ma. = 100: With external base-to-emitter resistance (ohms) $\leq 10$ . . . . .	$V_{CER(sus)}$	80	-	volts
With base ma. = 0 . . . . .	$V_{CEO(sus)}$	65	-	volts
DC Base-to-Emitter Saturation Voltage for dc collector ma. = 150, dc base ma. = 15 . . . . .	$V_{BE(sat)}$	-	1.1	volts
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = 150, dc base ma. = 15 . . . . .	$V_{CE(sat)}$	-	0.5	volt
DC Collector-Cutoff Current for dc collector volts = 60, dc emitter ma. = 0, case temperature <sup>b</sup> = 25° C . . . . .	$I_{CBO}$	-	0.002	$\mu a$
150° C . . . . .		-	2	$\mu a$
DC Emitter-Cutoff Current for dc base volts = 5, dc collector ma. = 0 . . . . .	$I_{EBO}$	-	0.002	$\mu a$
Input Resistance at frequency of 1 kc: With dc collector-to-emitter volts = 5, dc collector ma. = 1 . . . . .	$h_{ib}$	24	34	ohms
With dc collector-to-emitter volts = 10, dc collector ma. = 5 . . . . .		4	8	ohms
Input Capacitance for dc emitter volts = 0.5, dc collector ma. = 10 . . . . .	$C_{ib}$	-	80	$\mu f$



Output Capacitance for dc collector volts = 10, dc emitter ma. = 0. . . . .	$C_{ob}$	-	15	$\mu\mu f$
Output Conductance at frequency of 1 kc: With dc collector-to-emitter volts = 5, dc collector ma. = 1 . . . . .	$h_{ob}$	0.1	0.5	$\mu mho$
With dc collector-to-emitter volts = 10, dc collector ma. = 5. . . . .		0.1	1	$\mu mho$
Small-Signal Forward Current Transfer Ratio: With dc collector-to-emitter volts = 5, dc collector ma. = 1, frequency (kc) = 1 . . . . .	$h_{fe}$	30	100	
With dc collector-to-emitter volts = 10, dc collector ma. = 5, frequency (kc) = 1 . . . . .		35	150	
With dc collector-to-emitter volts = 10, dc collector ma. = 50, frequency (Mc) = 20. . . . .		3	-	
DC-Pulse Forward-Current Transfer Ratio for dc collector-to-emitter volts = 10, pulse duration ( $\mu sec$ ) = 300, duty factor of 0.018, dc collector ma. =	$h_{FE}$			
150. . . . .		40	120	
500. . . . .		25	-	
1000 . . . . .		10	-	
DC Forward Current Transfer Ratio: With dc collector-to-emitter volts = 10, dc collector ma. =	$h_{FE}$			
0.01 . . . . .		10	-	
0.1 . . . . .		20	-	
10 . . . . .		35	-	
With dc collector-to-emitter volts = 10, dc collector ma. = 10, case temperature <sup>b</sup> of $-55^{\circ} C$ . . . . .		20	-	
Voltage-Feedback Ratio at frequency of 1 kc: With dc collector-to-emitter volts = 5, dc collector ma. = 1. . . . .	$h_{rb}$	-	$3 \times 10^{-4}$	
With dc collector-to-emitter volts = 10, dc collector ma. = 5. . . . .		-	$3 \times 10^{-4}$	



# 2N2102

Noise Figure for signal frequency of 1 kc, circuit bandwidth of 15 kc, generator resistance (ohms) = 1000, dc collector-to-emitter volts = 10, dc collector ma. = 0.3.

NF	-	6	db
----	---	---	----

Total Switching Time<sup>d</sup> (Delay time + rise time + fall time).  $t_d+t_r+t_f$

	-	30	$\mu\text{sec}$
--	---	----	-----------------

Thermal Resistance:  $R_T$

Junction-to-case. . . . .	-	35	$^{\circ}\text{C}/\text{watt}$
Junction-to-free air. . . . .	-	175	$^{\circ}\text{C}/\text{watt}$

<sup>b</sup> Measured at center of seating plane.

<sup>d</sup> See accompanying *Total-Switching-Time Measurement Circuit*.

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the seating plane provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.

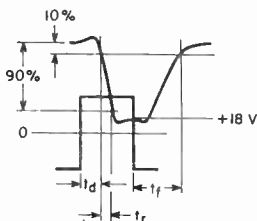
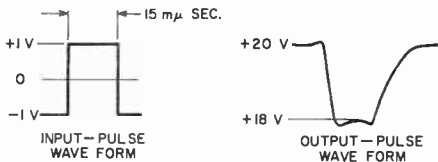
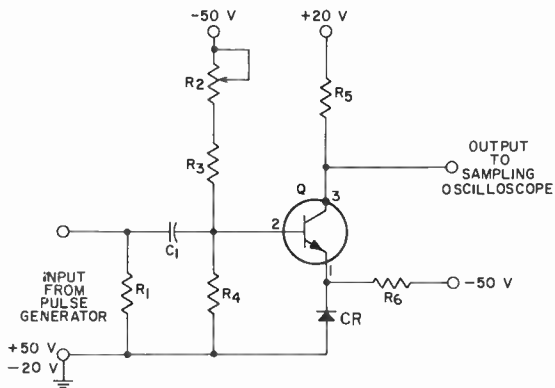
This transistor is intended for socketed, single-side printed-circuit boards and in conventional wire-in type circuits. If this transistor is used in double-side printed-circuit boards or in printed-circuit boards utilizing eyelets, it may be necessary to use an insulating washer or similar standoff device made of good dielectric material to prevent the solder from shorting the leads to each other or to the board, and to prevent the collector from shorting to ground.

It is to be noted that the case of this transistor operates at the collector voltage. Consideration, therefore, should be given to the possibility of shock hazard, if the case of this transistor is to operate at a voltage appreciably above or below ground potential. In such cases, suitable precautionary measures should be taken.





## TOTAL-SWITCHING-TIME MEASUREMENT CIRCUIT AND ASSOCIATED WAVE FORMS



92CS-11186R1

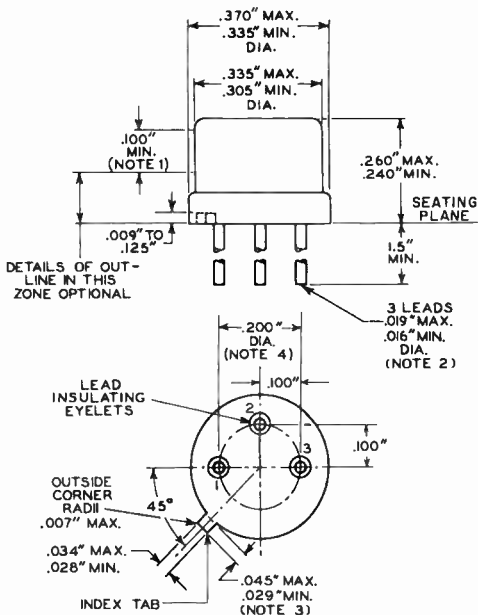
$C_1$ : 0.01  $\mu$ f  
 CR: Semiconductor diode  
 type 1N3064  
 Q: Transistor type 2N2102  
 $R_1$ : 100 ohms

$R_2$ : 1000 ohms  
 $R_3$ : 4700 ohms  
 $R_4$ : 100 ohms  
 $R_5$ : 40 ohms  
 $R_6$ : 1000 ohms, 5 watts



# 2N2102

JEDEC No. T0-5



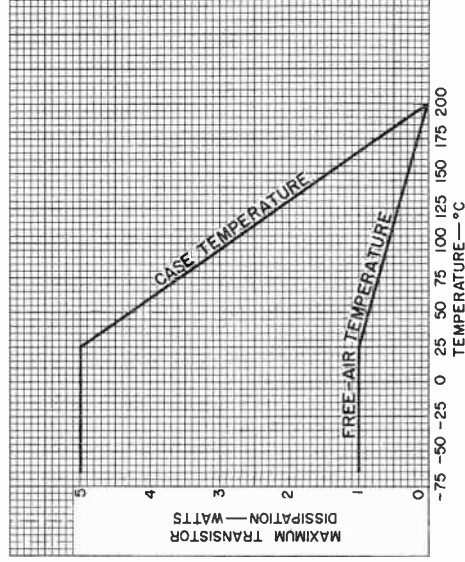
**NOTE 1:** THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE VARIATION IN ACTUAL DIAMETER WITHIN THE ZONE SHALL NOT EXCEED  $0.010''$ .

**NOTE 2:** THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN  $0.05''$  AND  $0.25''$  FROM THE SEATING PLANE. BETWEEN  $0.25''$  AND  $1.5''$  A MAXIMUM DIAMETER OF  $0.021''$  IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

**NOTE 3:** MEASURED FROM MAXIMUM DIAMETER OF THE ACTUAL DEVICE.

**NOTE 4:** LEADS HAVING MAXIMUM DIAMETER ( $0.019''$ ) MEASURED IN GAUGING PLANE  $0.054'' + 0.001'' - 0.000''$  BELOW THE SEATING PLANE OF THE DEVICE SHALL BE WITHIN  $0.007''$  OF THEIR TRUE LOCATIONS RELATIVE TO A MAXIMUM-WIDTH TAB.

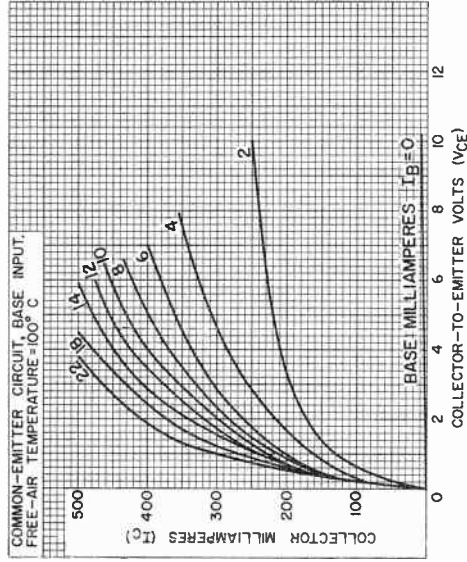
## RATING CHART



World Radio History

92CS-11172RI

## TYPICAL COLLECTOR CHARACTERISTICS

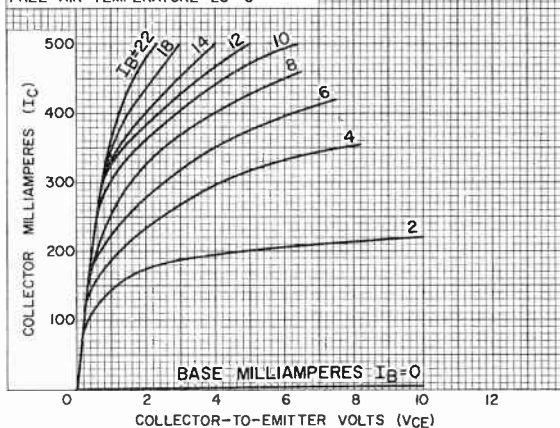


92CS-11177



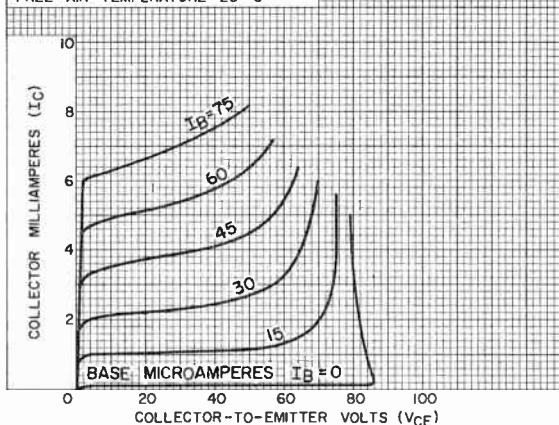
## TYPICAL COLLECTOR CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT.  
FREE-AIR TEMPERATURE = 25° C



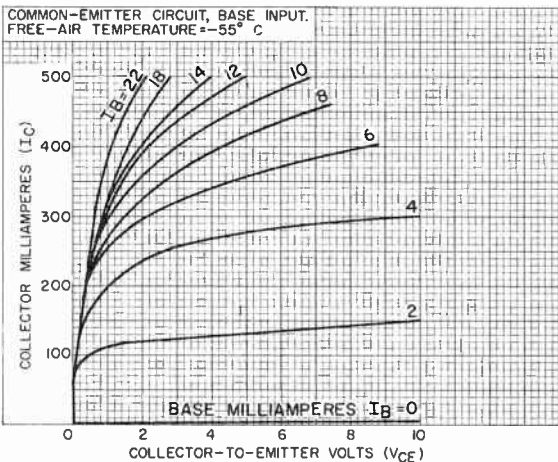
92CS-III76

COMMON-EMITTER CIRCUIT, BASE INPUT.  
FREE-AIR TEMPERATURE = 25° C



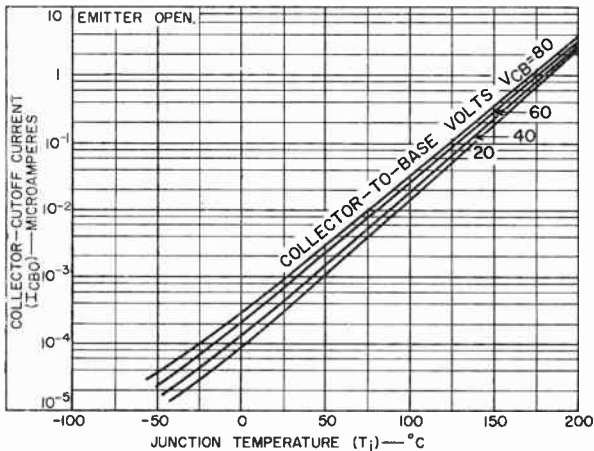
92CS-III75

## TYPICAL COLLECTOR CHARACTERISTICS



92CS-III90

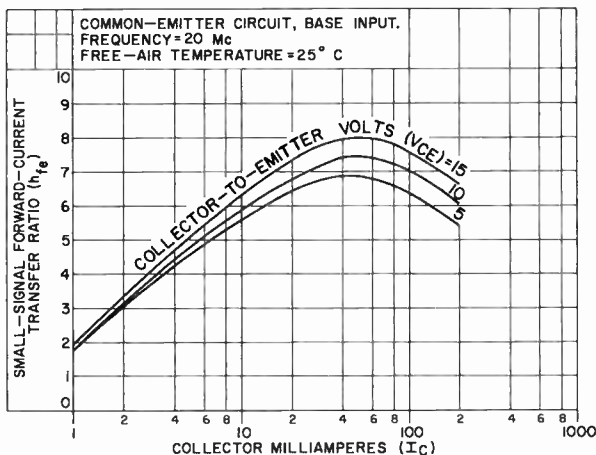
## TYPICAL COLLECTOR-CUTOFF-CURRENT CHARACTERISTICS



92CS-III70

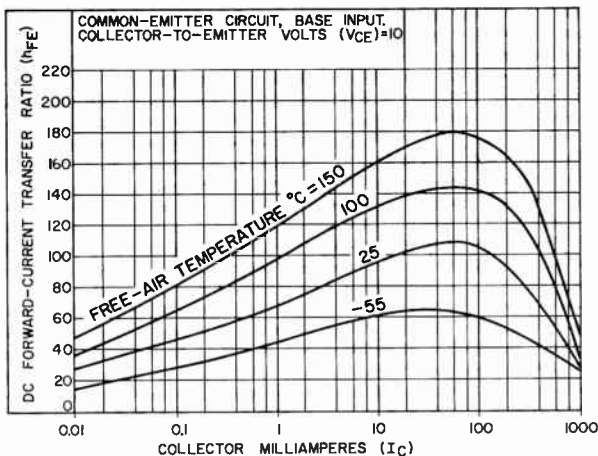


## TYPICAL SMALL-SIGNAL FORWARD-CURRENT TRANSFER-RATIO CHARACTERISTICS



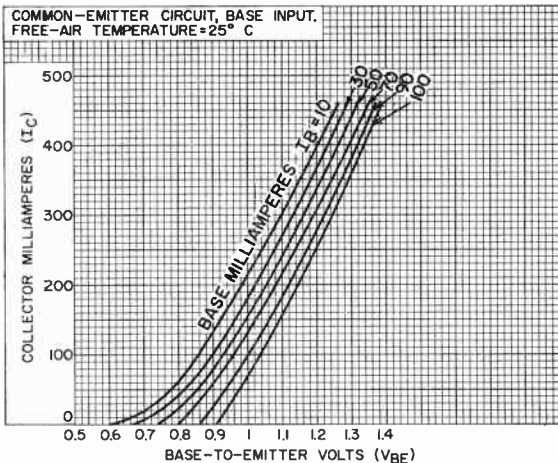
92CS-11171

## TYPICAL DC FORWARD-CURRENT TRANSFER-RATIO CHARACTERISTICS



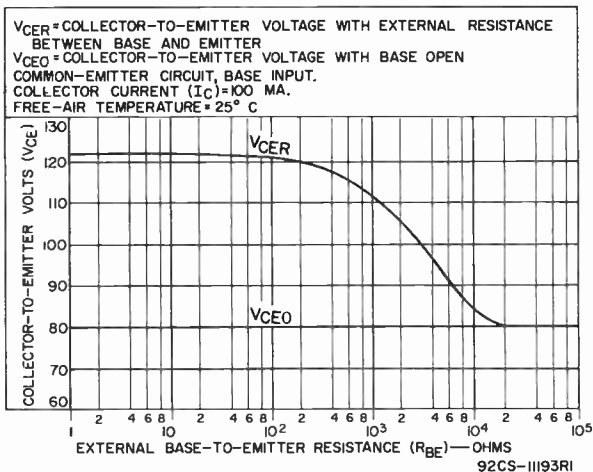
92CS-11181R1

## TYPICAL TRANSFER CHARACTERISTICS



92CS-11185

## TYPICAL COLLECTOR-TO-EMITTER-VOLTAGE CHARACTERISTICS

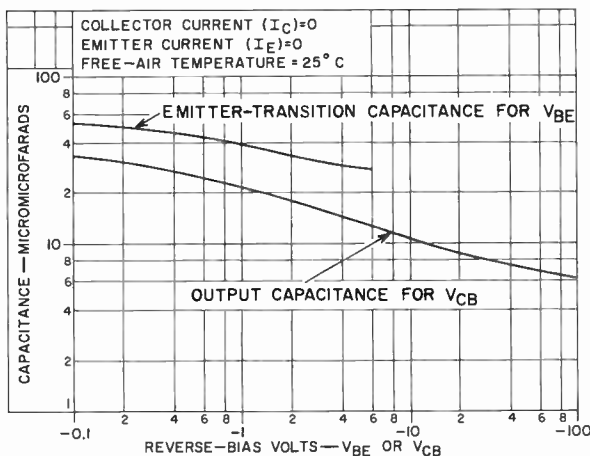


92CS-11193RI

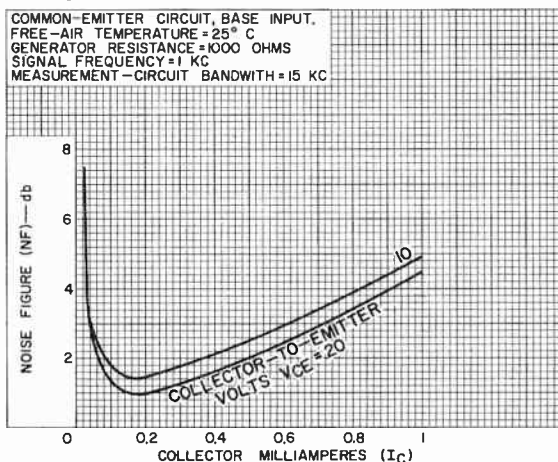


# 2N2102

## TYPICAL EMITTER-TRANSITION-CAPACITANCE AND OUTPUT-CAPACITANCE CHARACTERISTICS



## TYPICAL AF NOISE-FIGURE CHARACTERISTICS





# 2N2205

## Transistor

SILICON N-P-N DOUBLE-DIFFUSED-JUNCTION EPITAXIAL-PLANAR TYPE

For Switching Applications in  
Industrial and Military Equipment

The 2N2205 is the same as the 2N1708 except for the following items:

### GENERAL DATA

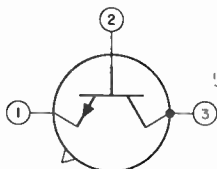
#### Mechanical:

Operating Position	Any
Maximum Length (Excluding flexible leads)	0.210"
Maximum Diameter	0.230"
Dimensional Outline	JFDEC No. T0-18
Case	Metal
Seals	Hermetic
Leads, Flexible	3
Minimum length	0.500"
Orientation and diameter	See <i>Dimensional Outline</i>

Terminal Diagram:

BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base

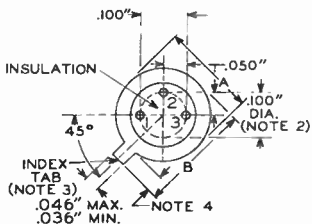
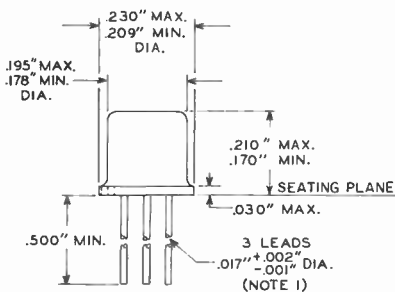


Lead 3 - Collector,  
Case



# 2N2205

JEDEC No. T0-18



92CS-10605R2

NOTE 1: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE SEATING PLANE. BETWEEN 0.25" TO THE END OF THE LEAD A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

NOTE 2: MAXIMUM DIAMETER LEADS AT A GAUGING PLANE 0.054"  $\pm$  0.001" - 0.000" BELOW SEATING PLANE TO BE WITHIN 0.007" OF THEIR TRUE LOCATION RELATIVE TO MAXIMUM WIDTH TAB AND TO THE MAXIMUM 0.230" DIAMETER MEASURED WITH A SUITABLE GAUGE. WHEN GAUGE IS USED, MEASUREMENT WILL BE MADE AT SEATING PLANE.

NOTE 3: FOR VISUAL ORIENTATION ONLY.

NOTE 4: TAB LENGTH TO BE 0.028" MINIMUM AND 0.048" MAXIMUM, AND WILL BE DETERMINED BY SUBTRACTING DIAMETER "A" FROM DIMENSION "B".

## Transistor

**SILICON N-P-N DOUBLE-DIFFUSED-JUNCTION EPITAXIAL-PLANAR TYPE**  
 For Switching Applications in  
 Industrial and Military Equipment

### GENERAL DATA

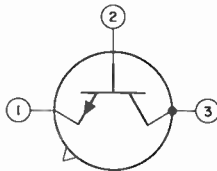
#### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.080"
Maximum Diameter . . . . .	0.230"
Dimensional Outline . . . . .	JEDEC No. TO-46
Case . . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	0.500"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>

Terminal Diagram:

BOTTOM VIEW

Lead 1 - Emitter  
 Lead 2 - Base



Lead 3 - Collector,  
 Case

### SWITCHING SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values:*

COLLECTOR-TO-BASE VOLTAGE:		
With emitter open . . . . .	$V_{CBO}$	25 max. volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With external resistance between base and emitter (ohms) = 1000, load resistance (ohms) = 100 . . . . .	$V_{CERL}$	20 max. volts
EMITTER-TO-BASE VOLTAGE:		
With collector open . . . . .	$V_{EBO}$	3 max. volts
COLLECTOR CURRENT . . . . .	$I_C$	Limited by power dissipation
TRANSISTOR DISSIPATION: <sup>a</sup>		
At case temperature <sup>b</sup> of 25° C or below . . . . .		1 max. watt
At free-air temperature of 25° C or below . . . . .		0.3 max. watt
TEMPERATURE RANGE:		
Storage . . . . .	-65 to +300	°C
Operating . . . . .	-65 to +175	°C
LEAD TEMPERATURE: <sup>c</sup>		
For 10 seconds maximum . . . . .		235 max. °C

<sup>a</sup> See accompanying *Rating Chart*.



# 2N2206

- <sup>b</sup> Measured at center of seating plane.  
<sup>c</sup> Measured  $1/16" \pm 1/32"$  down from seating plane.

## ELECTRICAL CHARACTERISTICS

*Voltage values are given with respect to base and free-air temperature of 25° C unless otherwise specified*

		Min.	Max.	
DC Collector Breakdown Voltage for dc collector ma. = 0.1, emitter ma. = 0 . . . . .	$V_{CBO}$	25	-	volts
DC Emitter Breakdown Voltage for dc emitter ma. = 0.1, collector ma. = 0 . . . . .	$V_{EBO}$	3	-	volts
DC Collector-to-Emitter Latching Voltage <sup>d</sup> for external resistance between base and emitter (ohms) = 1000, load resistance (ohms) = 100 . . . . .	$V_{CERL}$	20	-	volts
DC Base-to-Emitter Saturation Voltage for dc collector ma. = 10, dc base ma. = 1 . . . . .	$V_{BE(sat)}$	0.7	0.9	volt
DC Collector-to-Emitter Saturation Voltage: With dc collector ma. = 10, dc base ma. = 1 . . . . .	$V_{CE(sat)}$	-	0.22	volt
With dc collector ma. = 50, dc base ma. = 5 . . . . .		-	0.35	volt
DC Collector-Cutoff Current for dc collector volts = 15, emitter ma. = 0, free-air temperature = 25° C . . . . .	$I_{BCO}$	-	0.025	$\mu$ a
150° C . . . . .		-	15	$\mu$ a
DC Collector Current for base-to-emitter forward bias volts = 0.35, dc collector-to-emitter volts = 10, free-air temperature = 100° C . . . . .	$I_{CEX}$	-	15	$\mu$ a
Collector-to-Base Capacitance for dc collector volts = 10, emitter ma. = 0, frequency (kc) = 140. . . . .	$C_{ob}$	-	6	pf
DC Current Transfer Ratio for dc collector to emitter volts = 1, dc collector ma. = 10. . . . .	$h_{FE}$	40	120	
Small-Signal Current Transfer Ratio for dc collector-to-emitter volts = 10, dc collector ma. = 10, frequency (Mc) = 100 . . . . .	$h_{fe}$	2	-	



Storage Time <sup>e</sup> for dc collector supply volts = 10, collector resistance (ohms) = 1000, turn-on and turn-off dc base ma. = 10 each, dc collector ma. = 10 . . . . .	$t_s$	-	35	$\mu\text{sec}$
Turn-On Time <sup>f</sup> (Delay time + rise time) for dc collector supply volts = 3, turn-on dc base ma. = 3, turn-off dc base ma. = 1, dc collector ma. = 10 . . . . .	$t_d + t_r$	-	40	$\mu\text{sec}$
Turn-Off Time <sup>f</sup> (Storage time + fall-time) for dc collector supply volts = 3, turn-on dc base ma. = 3, turn-off dc base ma. = 1, dc collector ma. = 10 . . . . .	$t_s + t_f$	-	75	$\mu\text{sec}$

<sup>d</sup> For description of this test, write Commercial Engineering, Semiconductor & Materials Division, RCA, Somerville, New Jersey.

<sup>e</sup> See accompanying *Storage-Time-Measurement Circuit*.

<sup>f</sup> See accompanying *Turn-On-Time and Turn-Off-Time Measurement Circuit*.

### OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

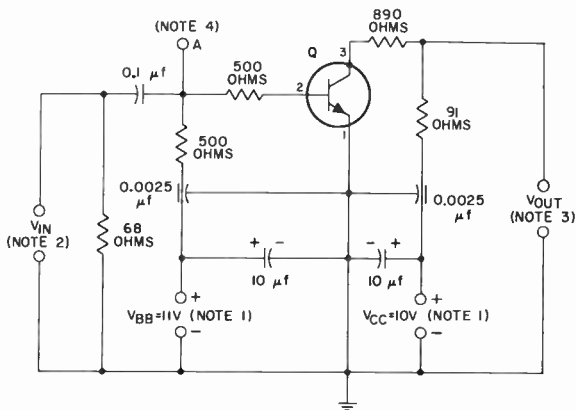
The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the seating plane provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.

It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.



# 2N2206

## STORAGE-TIME-MEASUREMENT CIRCUIT



92CS-11226R2

Q: Transistor type 2N2206

**NOTE 1:** WITH CERTAIN TYPES OF POWER SUPPLIES, IT MAY BE NECESSARY TO CONNECT 25- $\mu$ f DECOUPLING CAPACITORS ACROSS THE POWER-SUPPLY TERMINALS FOR VCC AND VBB.

**NOTE 2:** INPUT VOLTAGE ( $V_{IN}$ ) OBTAINED FROM MERCURY-RELAY TYPE PULSE GENERATOR HAVING AN OUTPUT IMPEDANCE OF 50 OHMS.

**NOTE 3:** THE ASSOCIATED INPUT AND OUTPUT WAVE FORMS SHOWN SHOULD BE MONITORED BY MEANS OF A SAMPLING OSCILLOSCOPE HAVING AN INPUT IMPEDANCE OF 50 OHMS.

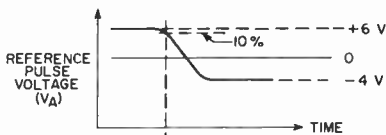
**NOTE 4:** TEST POINT FOR OBSERVATION OF REFERENCE PULSE VOLTAGE ( $V_A$ ).

## ASSOCIATED WAVE FORMS

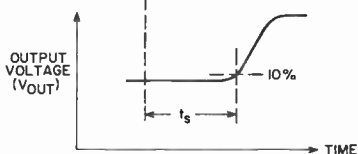


RISE TIME  $< 1\text{m}\mu\text{SEC}$   
 PULSE DURATION  $\geq 300\text{m}\mu\text{SEC}$   
 DUTY FACTOR  $< 0.02$

### INPUT WAVE FORM



REFERENCE WAVE FORM OBSERVED  
 AT POINT "A" IN STORAGE-TIME-  
 MEASUREMENT CIRCUIT



### OUTPUT WAVE FORM

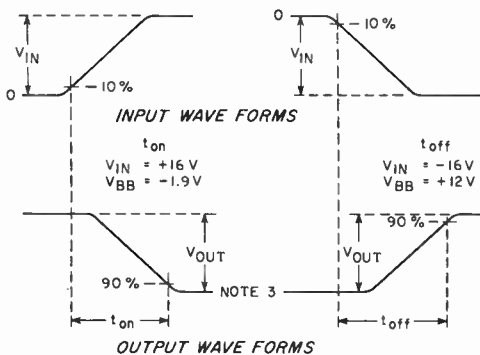
92CS-11224





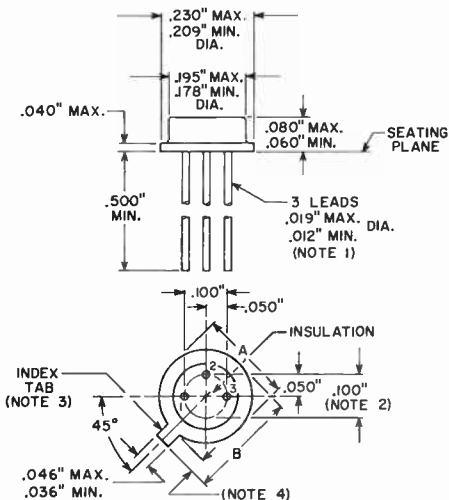


## ASSOCIATED WAVE FORMS



# 2N2206

JEDEC No. T0-46



92CS-11225

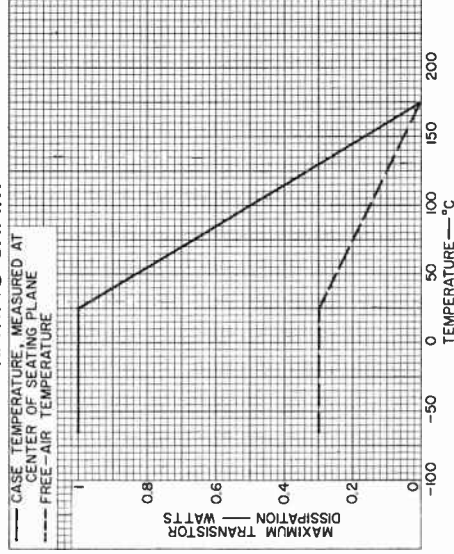
NOTE 1: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN  $0.05''$  AND  $0.25''$  FROM THE SEATING PLANE. BETWEEN  $0.25''$  TO THE END OF THE LEAD, A MAXIMUM DIAMETER OF  $0.021''$  IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

NOTE 2: MAXIMUM DIAMETER LEADS AT A GAUGING PLANE  $0.054'' \pm 0.001'' - 0.000''$  BELOW SEATING PLANE TO BE WITHIN  $0.007''$  OF THEIR TRUE LOCATION RELATIVE TO MAXIMUM WIDTH TAP AND TO THE  $0.230''$  MAXIMUM DIAMETER MEASURED WITH A SUITABLE GAUGE. WHEN GAUGE IS NOT USED, MEASUREMENT WILL BE MADE AT SEATING PLANE.

NOTE 3: INDEX TAB FOR VISUAL ORIENTATION ONLY.

NOTE 4: TAB LENGTH TO BE  $0.028''$  MINIMUM -  $0.048''$  MAXIMUM AND WILL BE DETERMINED BY SUBTRACTING DIAMETER "A" FROM DIMENSION "B".

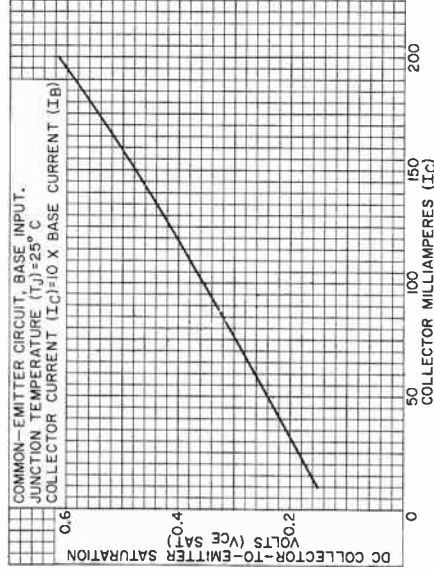
## RATING CHART



World Radio History

92CS-11223

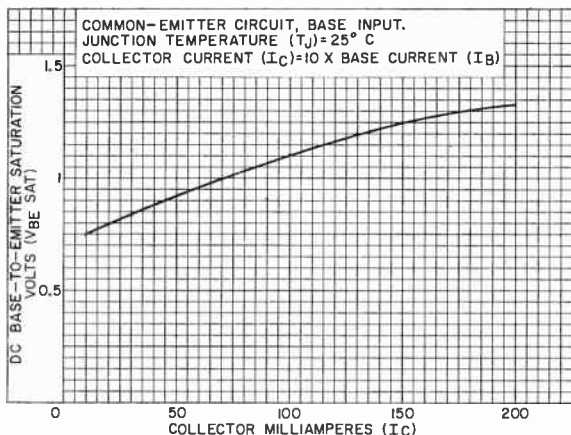
## TYPICAL DC COLLECTOR-TO-EMITTER SATURATION-VOLTAGE CHARACTERISTIC



92CS-11428

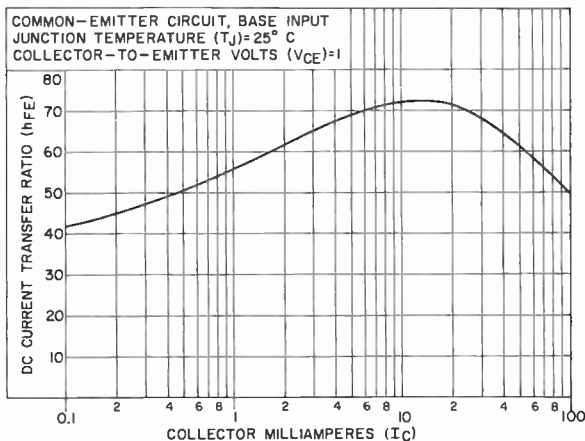


## TYPICAL DC BASE-TO-EMITTER SATURATION-VOLTAGE CHARACTERISTIC



92CS-11418

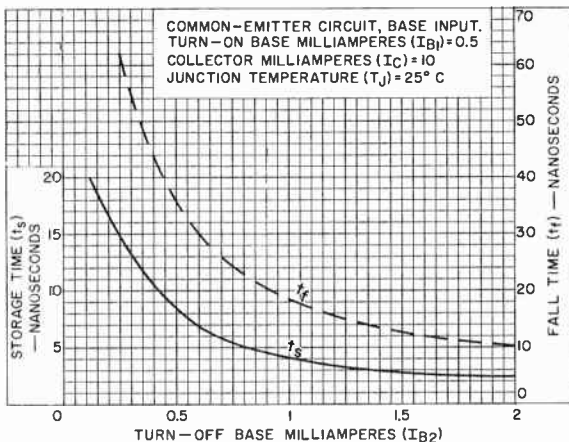
## TYPICAL DC CURRENT-TRANSFER-RATIO CHARACTERISTIC



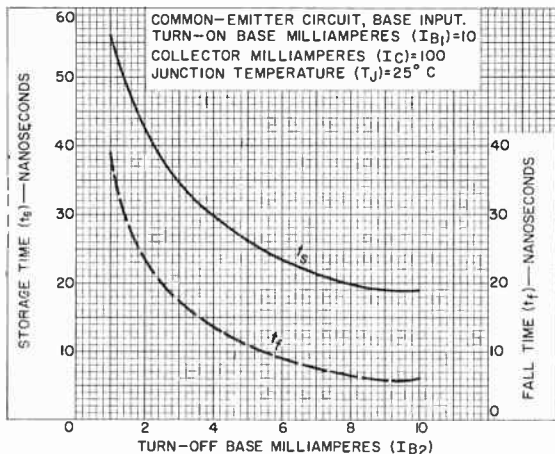
92CS-11431



## TYPICAL STORAGE-TIME AND FALL-TIME CHARACTERISTICS



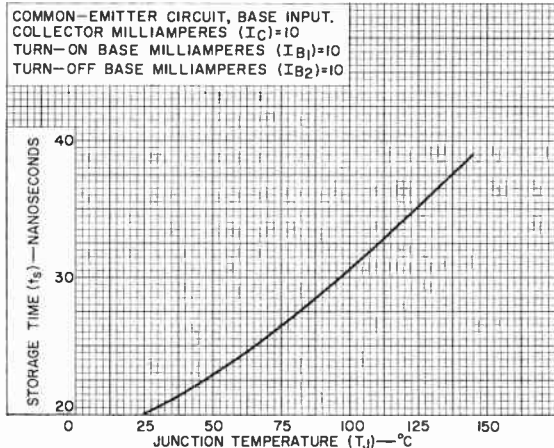
92CS-11427



92CS-11424

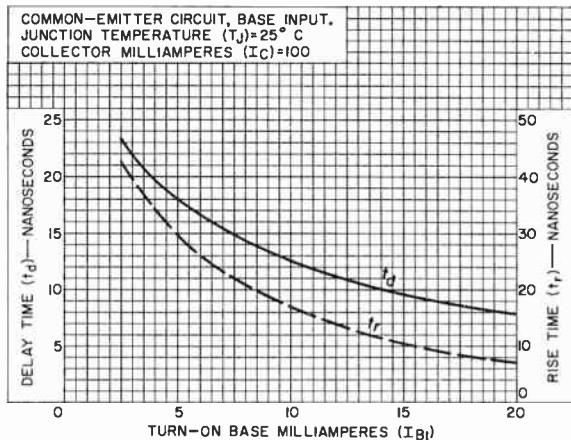


## TYPICAL STORAGE-TIME CHARACTERISTIC



92CS-11413

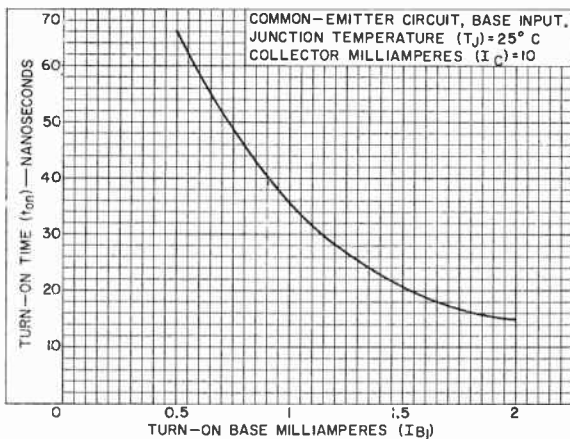
## TYPICAL DELAY-TIME AND RISE-TIME CHARACTERISTICS



92CS-11425



## TYPICAL TURN-ON-TIME CHARACTERISTIC



92CS-11416







## Transistor

### GERMANIUM P-N-P DIFFUSED-BASE MESA TYPE

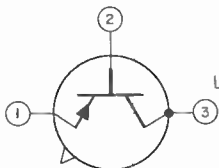
For IF- and RF-Amplifier Applications in the  
5-to-50 Mc Range in Industrial and Military Equipment

#### GENERAL DATA

##### Mechanical:

Dimensions . . . . . See Outline TO-18 in General Section  
Terminal Diagram: BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector,  
Case

#### RADIO-FREQUENCY AMPLIFIER

Maximum and Minimum Ratings, *Absolute-Maximum Values:*

COLLECTOR-TO-BASE VOLTAGE:			
With emitter open . . . . .	$V_{CBO}$	-25 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:			
With base open . . . . .	$V_{CEO}$	-15 max.	volts
EMITTER-TO-BASE VOLTAGE:			
With collector open . . . . .	$V_{EBO}$	-1 max.	volt
COLLECTOR CURRENT . . . . .	$I_C$	100 max.	ma
TRANSISTOR DISSIPATION:			
At free-air temperature of 25° C or below . . . . .		100 max.	mw
At free-air temperature above 25° C . . . . .		<i>Derate linearly 1.33 mw/°C</i>	
TEMPERATURE RANGE:			
Junction (Operating) . . . . .	$T_J$	-65 to +100	°C
Storage . . . . .	$T_{STG}$	-65 to +100	°C
LEAD TEMPERATURE: <sup>a</sup>			
For 10 seconds maximum . . . . .	$T_L$	235 max.	°C

#### ELECTRICAL CHARACTERISTICS

*Unless otherwise specified, free-air temperature = 25° C  
Min. Typical Max.*

DC Collector-to-Base Breakdown Voltage for dc collector ma. = -0.1, emitter cur- rent = 0 . . . . .	$BV_{CEO}$	-25	-	-	volts
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<sup>a</sup> measured 1/16" ± 1/32" along lead down from seating plane.



# 2N2273

		Min.	Typical	Max.	
DC Collector-to-Emitter Breakdown Voltage for dc collector ma. = -0.1, base current = 0 . . . . .	$BV_{CEO}$	-15	-	-	volts
DC Emitter-to-Base Breakdown Voltage for dc emitter ma. = -0.1, collector current = 0 . . . . .	$BV_{EBO}$	-1	-	-	volt
DC Collector-Cutoff Current for dc collector-to-base volts = -12, emitter current = 0 . . . . .	$I_{CBO}$	-	-	-10	$\mu a$
Base Spreading Resistance for dc collector-to-emitter volts = -10, dc collector ma. = -1, frequency (Mc) = 250 . . . . .	$r_{bb'}$	-	-	250	ohms
Real Part of Small-Signal Short-Circuit Input Impedance for dc collector-to-emitter volts = -9, dc collector ma. = -1, frequency (Mc) = 250.	$h_{ie}(\text{real})$	50	-	250	ohms
Output Capacitance for dc collector-to-base volts = -10, emitter current = 0, frequency (kc) = 140 . .	$C_{ob}$	-	-	3.5	pf
DC Forward-Current Transfer Ratio for dc collector-to-emitter volts = -10, dc collector ma. = -1.	$h_{FE}$	25	-	150	
Small-Signal Short-Circuit Forward-Current Transfer Ratio for dc collector-to-emitter volts = -6, dc collector ma. = -1, frequency (kc) = 1 . . . . .	$h_{fe}$	20	-	28	
Small-Signal Power Gain for dc collector-to-emitter volts = -9, dc collector ma. = -1, frequency (Mc) = 30 .	$G_{pe}$	10	-	-	db



## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the seating plane provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the seals of the leads and damage the transistor.

It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.



# 2N2475

## Transistor

### SILICON N-P-N EPITAXIAL-PLANAR TYPE

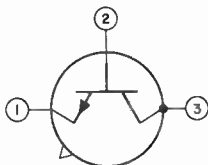
For Ultra-High-Speed Logic-Circuit Switching Applications  
in Commercial and Military Data-Processing Systems

#### GENERAL DATA

##### Mechanical:

Dimensions . . . . . Similar to JEDEC No. TO-18  
Terminal Diagram: BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector,  
Case

#### SWITCHING SERVICE

Maximum and Minimum Ratings, *Absolute-Maximum Values:*

COLLECTOR-TO-BASE VOLTAGE:			
With emitter open . . . . .	$V_{CBO}$	15 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:			
With base open . . . . .	$V_{CEO}$	6 max.	volts
EMITTER-TO-BASE VOLTAGE:			
With collector open . . . . .	$V_{EBO}$	4 max.	volts
COLLECTOR CURRENT . . . . .	$I_C$	Limited by power dissipation	
TRANSISTOR DISSIPATION: <sup>a</sup> P			
At case temperature <sup>b</sup> of			
100° C or below . . . . .		500 max.	mw
At free-air temperature of			
25° C or below . . . . .		300 max.	mw
TEMPERATURE RANGE:			
Junction (Operating) . . . . .	$T_J$	-65 to +200	°C
Storage . . . . .	$T_{STG}$	-65 to +300	°C
LEAD TEMPERATURE: <sup>c</sup>			
For 10 seconds maximum . . . . .	$T_L$	300 max.	°C

#### ELECTRICAL CHARACTERISTICS

*Unless otherwise specified, free-air temperature = 25° C*  
*Min. Typical Max.*

DC Collector Breakdown Voltage for dc collector ma. = 0.01, dc emitter current = 0. . . . .	$V_{CBO}$	15	30	-	volts
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<sup>a</sup> See accompanying Rating Chart.  
<sup>b</sup> Measured at center of seating plane.  
<sup>c</sup> Measured 1/16" ± 1/32" along lead, down from seating plane.



# 2N2475

		Min.	Typical	Max.	
DC Emitter Breakdown Voltage for dc collector current = 0, dc emitter ma. = 0.01. . . . .	$BV_{EBO}$	4	7	-	volts
DC Collector-to-Emitter Sustaining Voltage <sup>d</sup> for dc pulsed collector ma. = 10, dc base current = 0 . . . . .	$V_{CEO(sus)}$	6	10	-	volts
DC Base-to-Emitter Saturation Voltage for dc collector ma. = 20, dc base ma. = 0.66. . . . .	$V_{BE(sat)}$	0.8	0.9	1	volt
DC Collector-to-Emitter Saturation Voltage for dc collector ma. = 20, dc base ma. = 0.66. . . . .	$V_{CE(sat)}$	-	0.28	0.4	volt
DC Collector-Cutoff Current for dc collector-to-base volts = 5, dc emitter current = 0, free-air temperature = 25° C . . . . . 150° C. . . . .	$I_{CBO}$	-	0.002 0.9	0.05 5	$\mu a$ $\mu a$
Emitter-to-Base Capacitance for dc emitter-to-base volts = -0.5, dc collector current = 0, frequency (kc) = 140 (Approx.) . . . . .	$C_{ib}$	-	2	2.5	pf
Collector-to-Base Capacitance for dc collector-to-base volts = 5, dc emitter current = 0, frequency (kc) = 140 (Approx.) . . . . .	$C_{ob}$	-	2.4	3	pf
DC Forward-Current Transfer Ratio: With dc collector-to- emitter volts = 0.3, dc collector ma. = 1 . . . . . With dc collector-to- emitter volts = 0.5, dc pulsed collector ma. = 50. With dc collector-to- emitter volts = 0.4, dc pulsed collector ma. = 20. With dc collector-to- emitter volts = 0.4, dc pulsed collector ma. = 20, free-air temperature = -55° C. . . . .	$h_{FE}$	20 20 30 15	40 36 50 24	- - 150 -	
Small-Signal Short-Circuit Forward-Current Transfer Ratio for dc collector-to- emitter volts = 2, dc collector ma. = 20, signal frequency (Mc) = 100. . . . .	$h_{fe}$	6	8	-	



## Switching Time:

Storage time <sup>e</sup> for dc collector ma. = 5, turn-on dc base ma. = 5, turn-off dc base ma. = -5. . . . .	$t_s$	-	3.2	6	nsec
Turn-On time <sup>f</sup> (Delay time + rise time) for dc collector ma. = 20, turn-on dc base ma. = 1, turn-off dc base ma. = -1. . . . .	$t_{on}$	-	7.3	20	nsec
Turn-Off time <sup>f</sup> (Storage time + fall time) for dc collector ma. = 20, turn-on dc base ma. = 1, turn-off dc base ma. = -1. . . . .	$t_{off}$	-	9	15	nsec

<sup>d</sup> The Collector-to-Emitter Sustaining Voltage [ $V_{CEQ(sus)}$ ] with the base open is that value of voltage which remains relatively constant over a wide range of collector currents, and approximates the collector voltage at which the effective alpha of the device is equal to unity ( $V_{CEM} = 1$ ; voltage at which the product of alpha ( $\alpha$ ), at low voltage, times the multiplication factor ( $M$ ) equals unity).

<sup>e</sup> See accompanying *Storage-Time-Measurement Circuit*.

<sup>f</sup> See accompanying *Turn-On-Time and Turn-Off-Time Measurement Circuit*.

## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

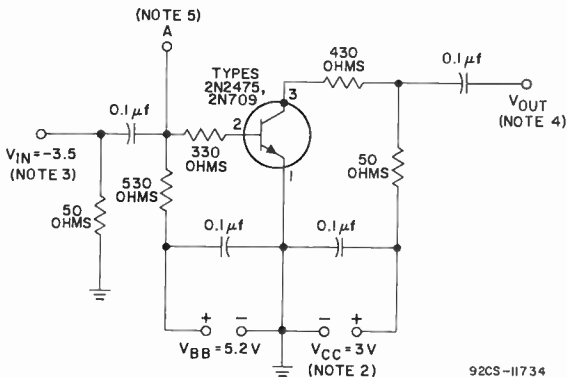
The *flexible Leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the seating plane provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the seals of the leads and damage the transistor.

It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.



# 2N2475

## STORAGE-TIME MEASUREMENT CIRCUIT



NOTE 1: ALL RESISTANCE VALUES HAVE  $\pm 1$  PERCENT TOLERANCE.

NOTE 2: WITH CERTAIN TYPES OF POWER SUPPLIES, IT MAY BE NECESSARY TO CONNECT 25- $\mu$ f DECOUPLING CAPACITORS ACROSS THE POWER-SUPPLY TERMINALS FOR  $V_{CC}$  AND  $V_{BB}$ .

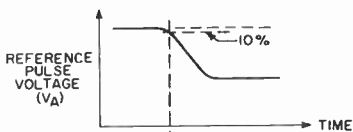
NOTE 3: INPUT VOLTAGE ( $V_{IN}$ ) OBTAINED FROM MERCURY-RELAY TYPE PULSE GENERATOR HAVING AN OUTPUT IMPEDANCE OF 50 OHMS.  $V_{IN}$  RISE TIME  $< 1$  NSEC; PULSE DURATION  $> 300$  NSEC; AND DUTY FACTOR  $< 0.02$ .

NOTE 4: INPUT AND OUTPUT WAVE FORMS SHOWN SHOULD BE MONITORED BY MEANS OF A SAMPLING OSCILLOSCOPE HAVING A RISE TIME  $< 0.5$  NSEC; INPUT CAPACITANCE OF PROBE  $\leq 2.5$  pf WITH SHUNT RESISTANCE  $> 1000$  OHMS.

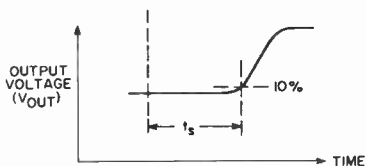
NOTE 5: TEST POINT FOR OBSERVATION OF REFERENCE PULSE VOLTAGE ( $V_A$ ).



## ASSOCIATED WAVE FORMS



REFERENCE WAVE FORM OBSERVED AT POINT "A" IN STORAGE-TIME MEASUREMENT CIRCUIT



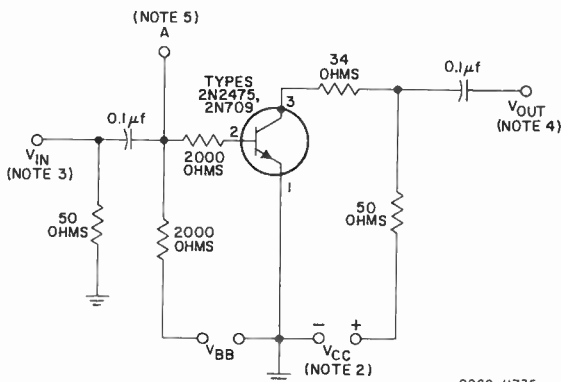
OUTPUT WAVE FORM

92CS-11728RI



# 2N2475

## TURN-ON-TIME AND TURN-OFF-TIME MEASUREMENT CIRCUIT



92CS-11735

### 2N2475

$t_{on}$   
 $V_{BB}$ : -1 volt  
 $V_{IN}$ : +4 volts  
 $V_{CC}$ : +1.8 volts

$t_{off}$   
 $V_{BB}$ : +5 volts  
 $V_{IN}$ : -4 volts  
 $V_{CC}$ : +1.8 volts

### 2N709

$t_{on}$   
 $V_{BB}$ : -1 volt  
 $V_{IN}$ : +6 volts  
 $V_{CC}$ : +1 volt

$t_{off}$   
 $V_{BB}$ : +5 volts  
 $V_{IN}$ : -4 volts  
 $V_{CC}$ : +1 volt

NOTE 1: ALL RESISTANCE VALUES HAVE  $\pm 1$  PER CENT TOLERANCE.

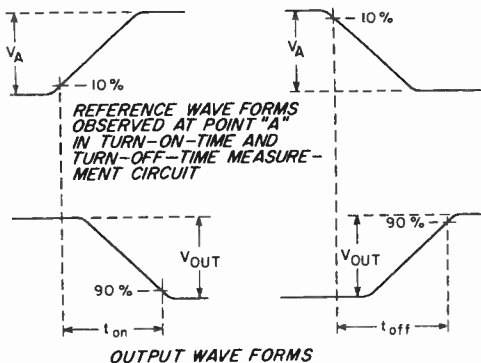
NOTE 2: WITH CERTAIN TYPES OF POWER SUPPLIES, IT MAY BE NECESSARY TO CONNECT 25- $\mu$ f DECOUPLING CAPACITORS ACROSS THE POWER-SUPPLY TERMINALS FOR  $V_{CC}$  AND  $V_{BB}$ .

NOTE 3: INPUT VOLTAGE ( $V_{IN}$ ) OBTAINED FROM MERCURY-RELAY TYPE PULSE GENERATOR HAVING AN OUTPUT IMPEDANCE OF 50 OHMS.  $V_{IN}$  RISE TIME  $< 1$  NSEC; PULSE DURATION  $> 300$  NSEC; AND DUTY FACTOR  $< 0.02$ .

NOTE 4: INPUT AND OUTPUT WAVE FORMS SHOWN SHOULD BE MONITORED BY MEANS OF A SAMPLING OSCILLOSCOPE HAVING A RISE TIME  $< 0.5$  NSEC; INPUT CAPACITANCE OF PROBE  $\leq 2.5$  pf WITH SHUNT RESISTANCE  $> 1000$  OHMS.

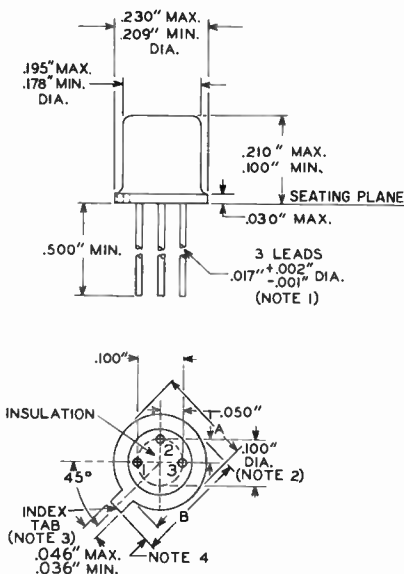
NOTE 5: TEST POINT FOR OBSERVATION OF REFERENCE PULSE VOLTAGE ( $V_A$ ).

## ASSOCIATED WAVE FORMS



# 2N2475

SIMILAR TO JEDEC No. T0-18



92CS-11739

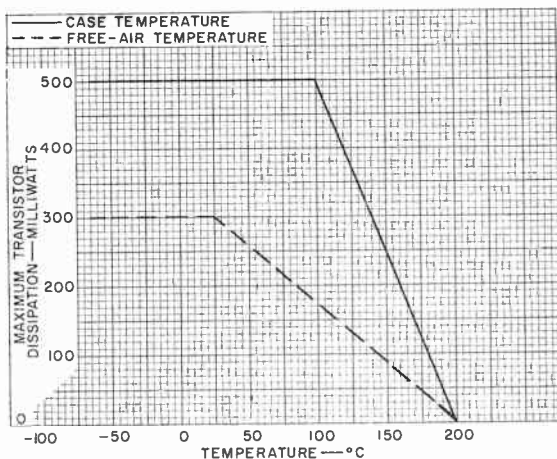
**NOTE 1:** THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE SEATING PLANE. BETWEEN 0.25" TO THE END OF THE LEAD, A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

**NOTE 2:** MAXIMUM DIAMETER LEADS AT A GAUGING PLANE 0.054" + 0.001" - 0.000" BELOW SEATING PLANE TO BE WITHIN 0.007" OF THEIR TRUE LOCATION RELATIVE TO MAXIMUM WIDTH TAB AND TO THE MAXIMUM 0.230" DIAMETER MEASURED WITH A SUITABLE GAUGE. WHEN GAUGE IS USED, MEASUREMENT WILL BE MADE AT SEATING PLANE.

**NOTE 3:** FOR VISUAL ORIENTATION ONLY.

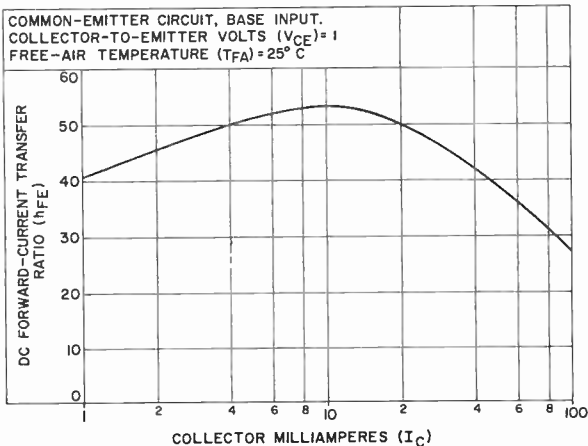
**NOTE 4:** TAB LENGTH TO BE 0.028" MINIMUM AND 0.046" MAXIMUM, AND WILL BE DETERMINED BY SUBTRACTING DIAMETER "A" FROM DIMENSION "B".

## RATING CHART



92CS-11733RI

## TYPICAL DC FORWARD-CURRENT-TRANSFER-RATIO CHARACTERISTIC

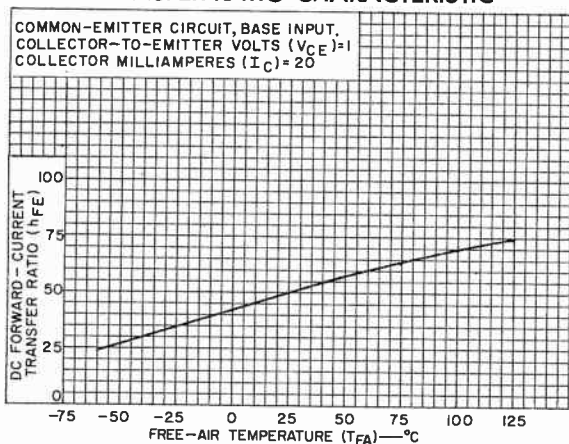


92CS-11731



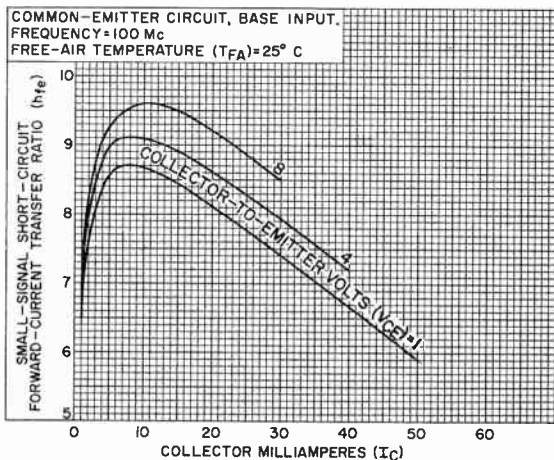
# 2N2475

## TYPICAL DC FORWARD-CURRENT-TRANSFER-RATIO CHARACTERISTIC



92CS-11724

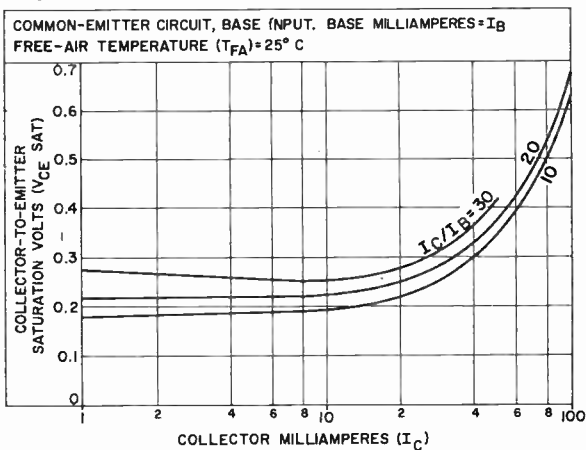
## TYPICAL SMALL-SIGNAL SHORT-CIRCUIT FORWARD-CURRENT TRANSFER-RATIO CHARACTERISTICS



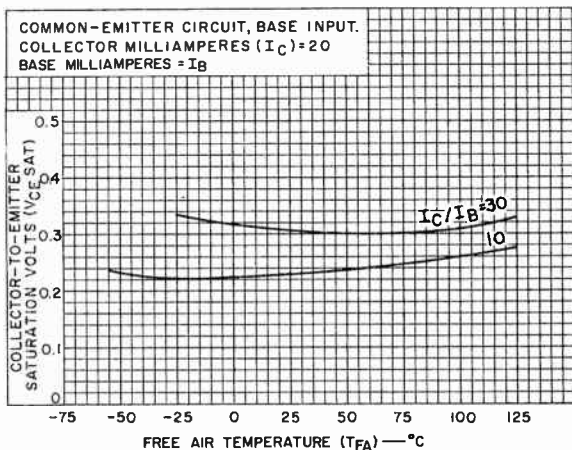
92CS-11725



## TYPICAL COLLECTOR-TO-EMITTER SATURATION-VOLTAGE CHARACTERISTICS



92CS-11732

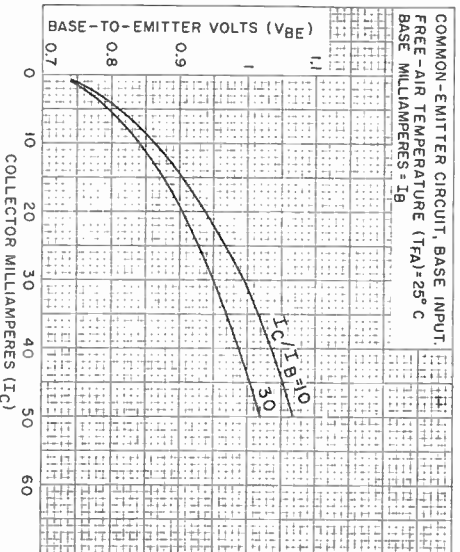


92CS-11730

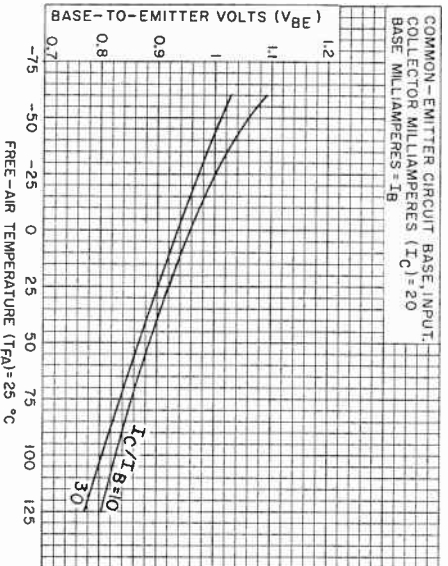


# 2N2475

## TYPICAL BASE-TO-EMITTER VOLTAGE CHARACTERISTICS



92CS-11727

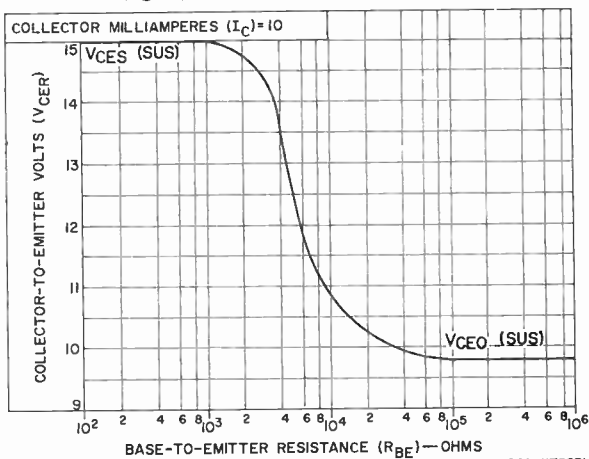


92CS-11726

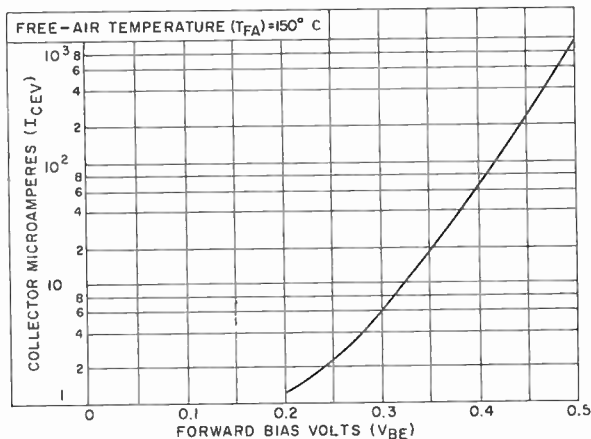




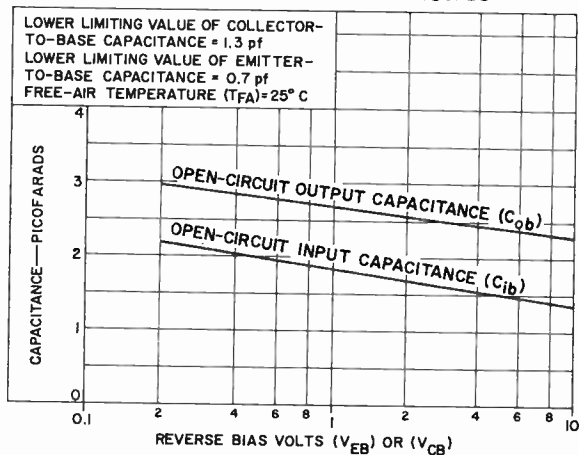
## TYPICAL COLLECTOR-TO-EMITTER VOLTAGE CHARACTERISTICS



## TYPICAL COLLECTOR-CURRENT CHARACTERISTIC



## TYPICAL INPUT- AND OUTPUT- CAPACITANCE CHARACTERISTICS



## Transistor

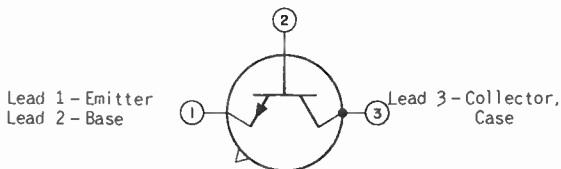
**SILICON N-P-N DOUBLE-DIFFUSED-JUNCTION EPITAXIAL-PLANAR TYPE**  
**For High-Speed, High-Current Switching in Core-Driving and Line-Driving Applications in Data-Processing Systems**

### GENERAL DATA

#### Mechanical:

Dimensions. . . . . See Outline T0-5 in General Section

Terminal Diagram: **BOTTOM VIEW**



### SWITCHING SERVICE

**Maximum and Minimum Ratings, Absolute-Maximum Values:**

<b>COLLECTOR-TO-BASE VOLTAGE:</b>			
With emitter open . . . . .	$V_{CBO}$	60 max.	volts
<b>COLLECTOR-TO-EMITTER VOLTAGE:</b>			
With base open. . . . .	$V_{CEO}$	20 max.	volts
<b>EMITTER-TO-BASE VOLTAGE:</b>			
With collector open . . . . .	$V_{EBO}$	5 max.	volts
<b>COLLECTOR CURRENT</b> . . . . .	$I_C$	Limited by power dissipation	
<b>TRANSISTOR DISSIPATION:<sup>a</sup></b>			
P			
At case temperature <sup>b</sup> of			
25° C or below. . . . .		2 max.	watts
At free-air temperature of			
25° C or below. . . . .		0.6 max.	watt
<b>TEMPERATURE RANGE:</b>			
Junction (Operating). . . . .	$T_J$	-65 to +200	°C
Storage . . . . .	$T_{STG}$	-65 to +300	°C
<b>LEAD TEMPERATURE:<sup>c</sup></b>			
For 10 seconds maximum. . . . .	$T_L$	235 max.	°C

### ELECTRICAL CHARACTERISTICS

*Unless otherwise specified, free-air temperature = 25° C*

	<i>Min.</i>	<i>Max.</i>	
--	-------------	-------------	--

<b>DC Collector-to-Base Breakdown</b>			
Voltage for dc collector $\mu a$			
= 10, emitter current = 0 . . . . .			
	$BV_{CBO}$	60	- volts

<sup>a</sup> See accompanying Rating Chart.  
<sup>b</sup> Measured at center of seating plane.  
<sup>c</sup> Measured 1/16" ± 1/32" along lead down from seating plane.



# 2N2476

		Min.	Max.	
DC Collector-to-Emitter Breakdown Voltage for pulse dc collector ma. = 50 <sup>d</sup> , base current = 0 . . . . .	$V_{CE0}$	20	-	volts
DC Emitter-to-Base Breakdown Voltage for dc emitter ma. = 0.1, collector current = 0 . . . . .	$V_{EBO}$	5	-	volts
DC Base-to-Emitter Voltage for dc collector ma. = 150, dc base ma. = 7.5 . . . . .	$V_{BE}$	-	1	volt
DC Collector-to-Emitter Saturation Voltage: $V_{CE(sat)}$				
With dc collector ma. = 150, dc base ma. = 7.5 . . . . .		-	0.4	volt
With dc collector ma. = 500, dc base ma. = 50 . . . . .		-	0.75	volt
DC Collector-Cutoff Current for dc collector-to-base volts = 30, emitter current = 0, free-air temperature =	$I_{CBO}$			
25° C . . . . .		-	0.2	$\mu$ a
150° C . . . . .		-	200	$\mu$ a
DC Emitter-Cutoff Current for dc emitter-to-base volts = 5, collector current = 0 . . . . .	$I_{EBO}$	-	100	$\mu$ a
Output Capacitance for dc collector-to-base volts = 10, emitter current = 0, frequency (kc) = 140.	$C_{ob}$	-	10	pf
DC Forward-Current Transfer Ratio for dc collector-to-emitter volts = 0.4, dc collector ma. = 150.	$h_{FE}$	20	-	
Small-Signal Short-Circuit Forward-Current Transfer Ratio for dc collector-to-emitter volts = 10, dc collector ma. = 50, frequency (Mc) = 100. . .	$h_{fe}$	2.5	-	
Switching Time:				
Storage time <sup>e</sup> for dc collector supply volts = 6.4, collector resistance (ohms) = 40, turn-on dc base ma. = 15, turn-off dc base ma. = -15, dc collector ma. = 150 . . . . .	$t_s$	-	25	nsec
Turn-on time <sup>f</sup> (Delay time + rise time) for dc collector supply volts = 6.4, turn-on dc base ma. = 15, dc collector ma. = 150 . . . . .	$t_{on}$	-	25	nsec
Turn-off time <sup>g</sup> (Storage time + fall time) for dc collector supply volts = 6.4, turn-on dc base ma. = 15, turn-off dc base ma. = -15, dc collector ma. = 150 . . . . .	$t_{off}$	-	45	nsec



d Pulse duration  $\leq 400 \mu\text{sec}$ , duty factor = 0.03.

e See accompanying *Storage-Time and Turn-Off-Time Measurement Circuit*.

f See accompanying *Turn-On-Time Measurement Circuit*.

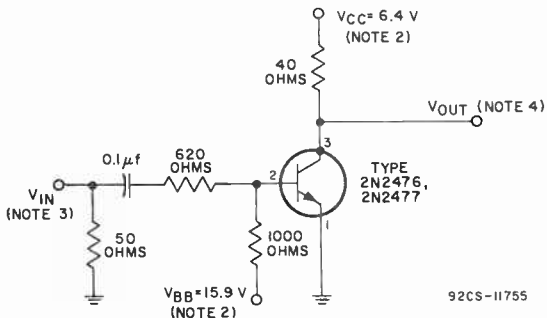
### OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The flexible leads of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the seating plane provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the seals of the leads and damage the transistor.

It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.

### STORAGE-TIME AND TURN-OFF-TIME MEASUREMENT CIRCUIT



NOTE 1: ALL RESISTANCE VALUES HAVE  $\pm 1$  PERCENT TOLERANCE.

NOTE 2: WITH CERTAIN TYPES OF POWER SUPPLIES, IT MAY BE NECESSARY TO CONNECT 25- $\mu\text{f}$  DECOUPLING CAPACITORS ACROSS THE POWER-SUPPLY TERMINALS FOR  $V_{CC}$  AND  $V_{BB}$ .

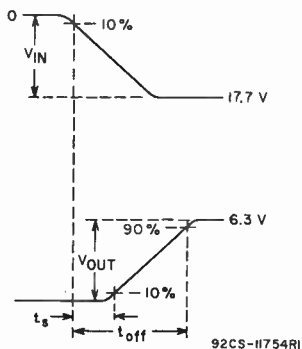
NOTE 3: INPUT VOLTAGE ( $V_{IN}$ ) OBTAINED FROM MERCURY-RELAY TYPE PULSE GENERATOR HAVING AN OUTPUT IMPEDANCE OF 50 OHMS.  $V_{IN}$  RISE TIME  $< 2$  NANoseconds; PULSE DURATION  $> 150$  NANoseconds; DUTY FACTOR  $< 0.02$ .

NOTE 4: THE ASSOCIATED INPUT AND OUTPUT WAVE FORMS SHOWN SHOULD BE MONITORED BY MEANS OF A SAMPLING OSCILLOSCOPE HAVING A RISE TIME  $< 0.5$  NANoseCOND; INPUT CAPACITANCE OF PROBE  $< 2.5$  PICOFARADS WITH SHUNT RESISTANCE OF 1 MEGOHM.

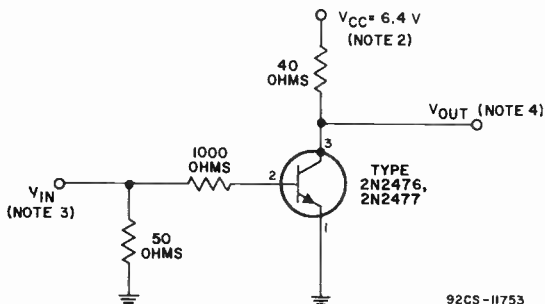


# 2N2476

## ASSOCIATED WAVE FORMS



## TURN-ON-TIME MEASUREMENT CIRCUIT



**NOTE 1:** ALL RESISTANCE VALUES HAVE  $\pm 1$  PERCENT TOLERANCE.

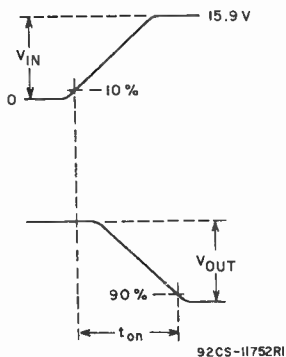
**NOTE 2:** WITH CERTAIN TYPES OF POWER SUPPLIES, IT MAY BE NECESSARY TO CONNECT  $25\text{-}\mu\text{f}$  DECOUPLING CAPACITORS ACROSS THE POWER-SUPPLY TERMINALS FOR  $V_{CC}$  AND  $V_{BB}$ .

**NOTE 3:** INPUT VOLTAGE ( $V_{IN}$ ) OBTAINED FROM MERCURY-RELAY TYPE PULSE GENERATOR HAVING AN OUTPUT IMPEDANCE OF 50 OHMS.  $V_{IN}$  RISE TIME  $< 2$  NANoseconds; PULSE DURATION  $> 150$  NANoseconds AND DUTY FACTOR  $< 0.02$ .

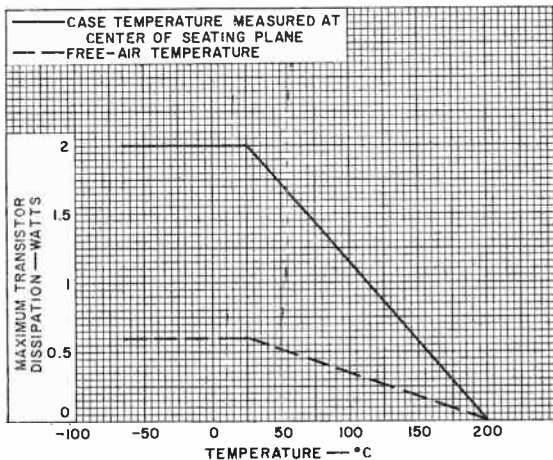
**NOTE 4:** THE ASSOCIATED INPUT AND OUTPUT WAVE FORMS SHOWN SHOULD BE MONITORED BY MEANS OF A SAMPLING OSCILLOSCOPE HAVING A RISE TIME  $< 0.5$  NANoseCOND; INPUT CAPACITANCE OF PROBE  $< 2.5$  PICOFARADS WITH SHUNT RESISTANCE OF 1 MEGOHM.



## ASSOCIATED WAVE FORMS



## RATING CHART

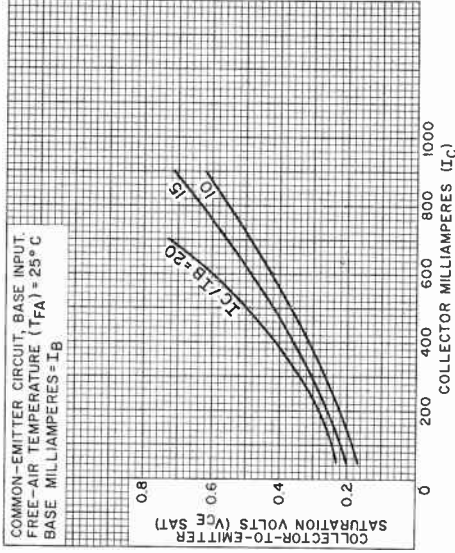


92CS-11751RI



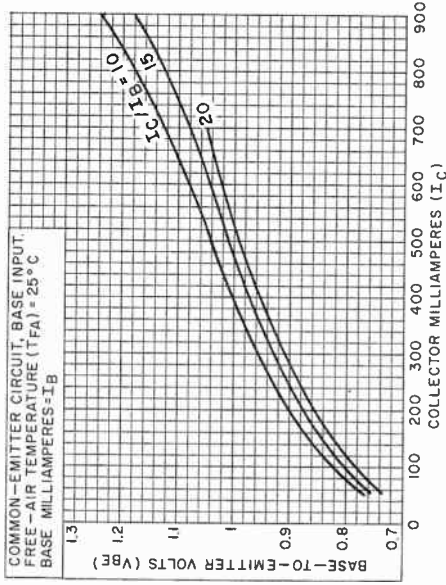
# 2N2476

## TYPICAL COLLECTOR-TO-EMITTER SATURATION-VOLTAGE CHARACTERISTICS



92CS-11768

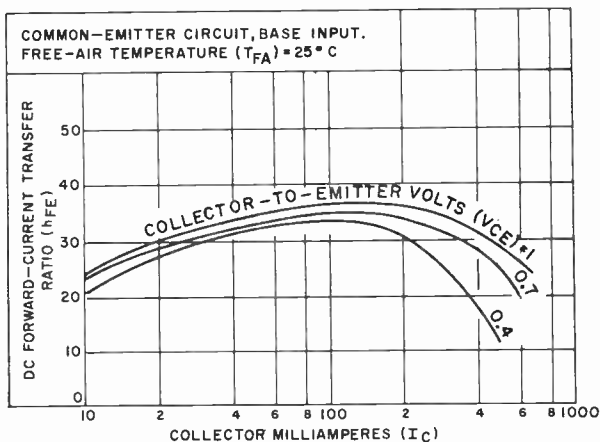
## TYPICAL BASE-TO-EMITTER VOLTAGE CHARACTERISTICS



92CS-11767

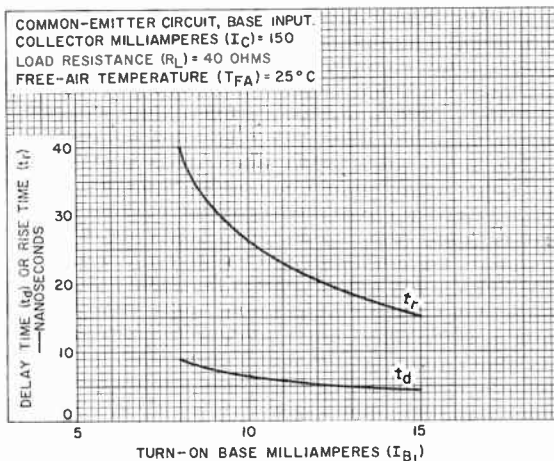


## TYPICAL DC FORWARD-CURRENT TRANSFER-RATIO CHARACTERISTICS



92CS-11761

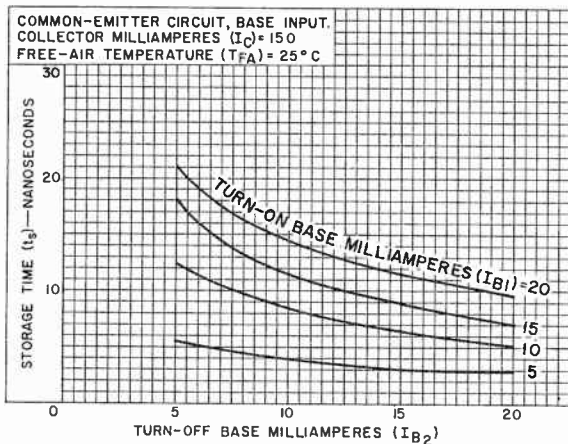
## TYPICAL DELAY-TIME AND RISE-TIME CHARACTERISTICS



92CS-11762



## TYPICAL STORAGE-TIME CHARACTERISTICS



92CS-11769

## Transistor

**SILICON N-P-N DOUBLE-DIFFUSED-JUNCTION EPITAXIAL-PLANAR TYPE**

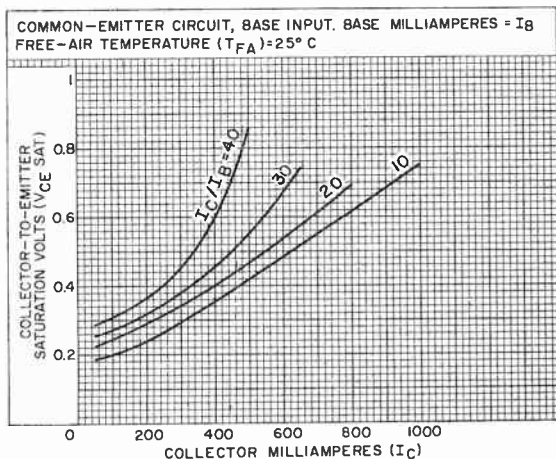
For High-Speed, High-Current Switching in Core-Driving  
and Line-Driving Applications in Data-Processing Systems

The 2N2477 is the same as the 2N2476 except for the following items:

### ELECTRICAL CHARACTERISTICS

	Min.	Max.	
DC Base-to-Emitter Voltage for dc collector ma. = 150, dc base ma. = 3.75 . . . . .	$V_{BE}$	- 0.95	volt
DC Collector-to-Emitter Saturation Voltage:	$V_{CE(sat)}$		
With dc collector ma. = 150, dc base ma. = 3.75 . . . . .		- 0.4	volt
With dc collector ma. = 500, dc base ma. = 50 . . . . .		- 0.65	volt
DC Forward-Current Transfer Ratio for dc collector-to- emitter volts = 0.4, dc collector ma. = 150 . . . . .	$h_{FE}$	40 -	

### TYPICAL COLLECTOR-TO-EMITTER SATURATION-VOLTAGE CHARACTERISTICS

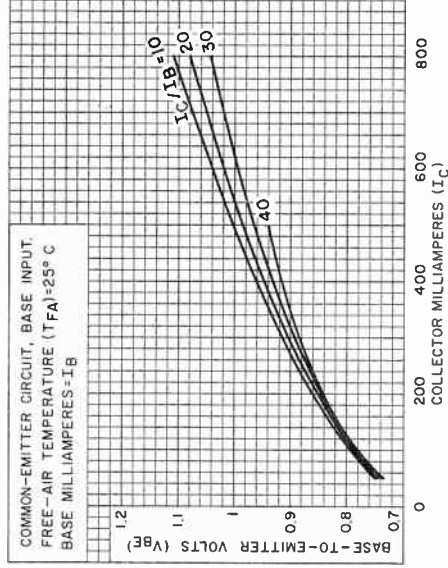


92CS-11758

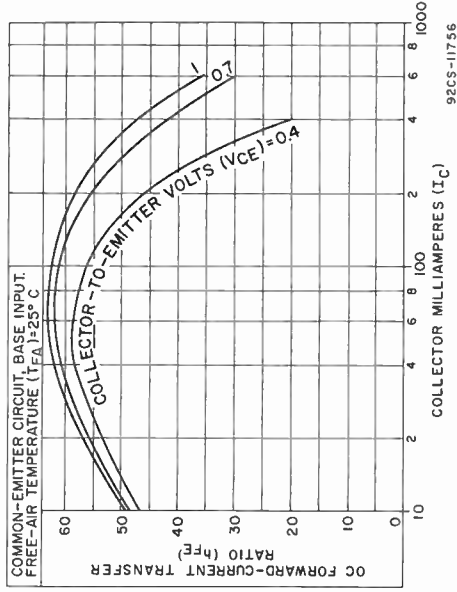


# 2N2477

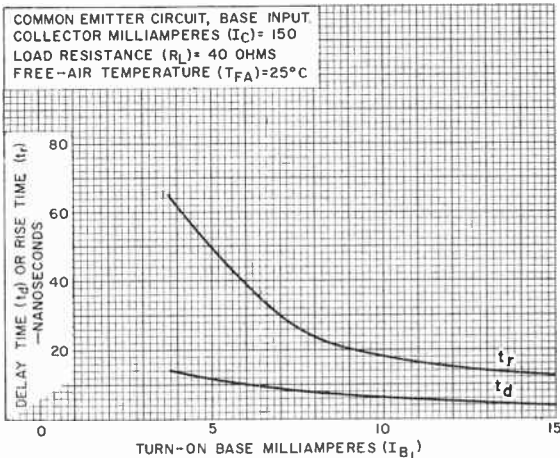
## TYPICAL BASE-TO-EMITTER VOLTAGE CHARACTERISTICS



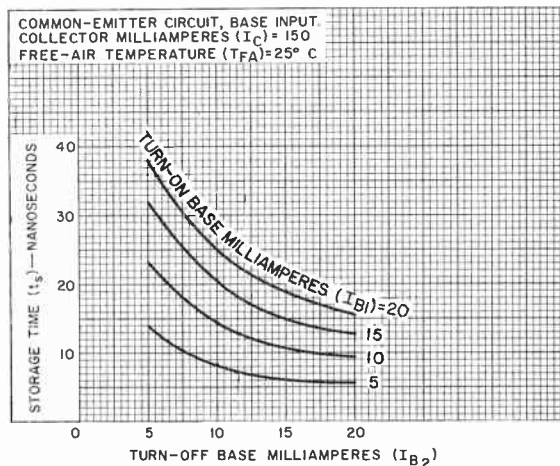
## TYPICAL DC FORWARD-CURRENT TRANSFER-RATIO CHARACTERISTICS



## TYPICAL DELAY-TIME AND RISE-TIME CHARACTERISTICS



## TYPICAL STORAGE-TIME CHARACTERISTICS





## Transistor

### GERMANIUM N-P-N DIFFUSED-BASE MESA TYPE

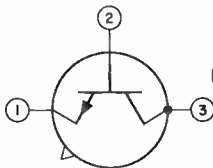
For Low-Power RF-Amplifier Applications in the VHF Range in Industrial and Military Equipment

#### GENERAL DATA

##### Mechanical:

Dimensions . . . . . See Outline TO-18 in General Section  
Terminal Diagram: BOTTOM VIEW

Lead 1 - Emitter  
Lead 2 - Base



Lead 3 - Collector,  
Case

#### RADIO-FREQUENCY AMPLIFIER

Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE:			
With emitter open . . . . .	$V_{CBO}$	20 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:			
With base open . . . . .	$V_{CEO}$	12 max.	volts
EMITTER-TO-BASE VOLTAGE:			
With collector open . . . . .	$V_{EBO}$	3 max.	volts
COLLECTOR CURRENT . . . . .	$I_C$	100 max.	ma
TRANSISTOR DISSIPATION:			
At free-air temperature of			
25° C or below . . . . .		150 max.	mw
At free-air temperature			
above 25° C . . . . .		<i>Derate linearly 2 mw/°C</i>	
TEMPERATURE RANGE:			
Junction (Operating) . . . . .	$T_J$	-65 to +100	°C
Storage . . . . .	$T_{STG}$	-65 to +100	°C
LEAD TEMPERATURE: <sup>a</sup>			
For 10 seconds maximum . . . . .	$T_L$	235 max.	°C

#### ELECTRICAL CHARACTERISTICS

Unless otherwise specified, free-air temperature = 25° C  
Min. Typical Max.

DC Collector-to-Base			
Breakdown Voltage for			
dc collector ma. = 0.1,			
emitter current = 0 . . . . .			
$BV_{CBO}$	20	-	- volts

<sup>a</sup> Measured 1/16" ± 1/32" along lead down from seating plane.



# 2N2482

Min. Typical Max.

	Min.	Typical	Max.	
DC Collector-to-Emitter Breakdown Voltage for dc collector ma. = 2, base short-circuited to emitter. . . . .	$BV_{CES}$	15	-	- volts
DC Emitter-to-Base Breakdown Voltage for dc emitter ma. = 0.1, collector current = 0 . . . . .	$BV_{EBO}$	3	-	- volts
DC Collector-Cutoff Current for dc collector-to-base volts = 6, emitter current = 0, free air temperature =	$I_{CBO}$			
25° C . . . . .		-	-	5 $\mu$ a
80° C . . . . .		-	-	90 $\mu$ a
Base Spreading Resistance for dc collector-to-emitter volts = 6, dc collector ma. = 10, frequency (Mc) = 250. . . . .	$r_{bb'}$	-	30	- ohms
Output Capacitance for dc collector-to-base volts = 6, emitter current = 0, frequency (kc) = 140. . . . .	$C_{ob}$	-	-	4.5 pf
DC Forward-Current Transfer Ratio for dc collector-to-emitter volts = 6, dc collector ma. = 2 . . . . .	$h_{FE}$	25	-	200
Small-Signal Short-Circuit Forward-Current Transfer Ratio:	$h_{fe}$			
With dc collector-to-emitter volts = 6, dc collector ma. = 2, frequency (kc) = 1. . . . .		15	-	175
With dc collector-to-emitter volts = 10, dc collector ma. = 10, frequency (Mc) = 100. . . . .		6	10	-
With dc collector-to-emitter volts = 1.7, dc collector ma. = 85, frequency (Mc) = 100. . . . .		3	-	-
Noise Figure for dc collector-to-emitter volts = 6, dc collector ma. = 2, frequency (Mc) =	NF			
30. . . . .		-	5	- db
100 . . . . .		-	6	- db



Small-Signal Power Gain:	$G_{pe}$			
With dc collector-to-emitter volts = 6, dc collector ma. = 2, frequency (Mc) =				
30 . . . . .	-	25	-	db
100 <sup>b</sup> . . . . .	-	12	-	db
With dc collector-to-emitter volts = 12, dc collector ma. = 10, frequency (Mc) = 200 . .	-	8	-	db
Collector-to-Base Time Constant for dc collector-to-base volts = 6, dc collector ma. = 2, frequency (Mc) = 31.9 . .	$r_{b1}C_c$	-	-	0.3 nsec
Power Output as class A amplifier <sup>c</sup> for dc collector-to-emitter volts = 12, dc collector ma. = 30, signal input (mw) = 6.5, frequency (Mc) = 70 . . . . .		-	150	- mw

<sup>b</sup> Circuit is neutralized and matched.

<sup>c</sup> See accompanying *Power-Output-Measurement Circuit*.

### OPERATING CONSIDERATIONS

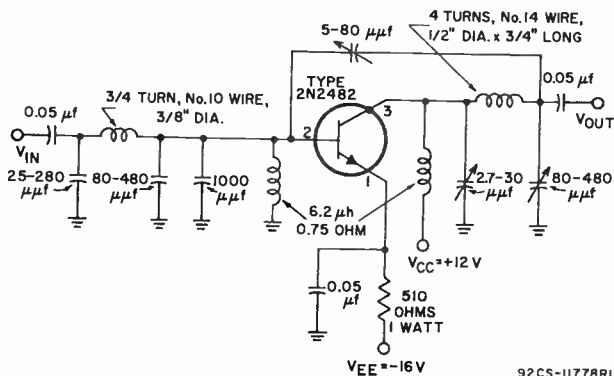
It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the seating plane provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the seals of the leads and damage the transistor.

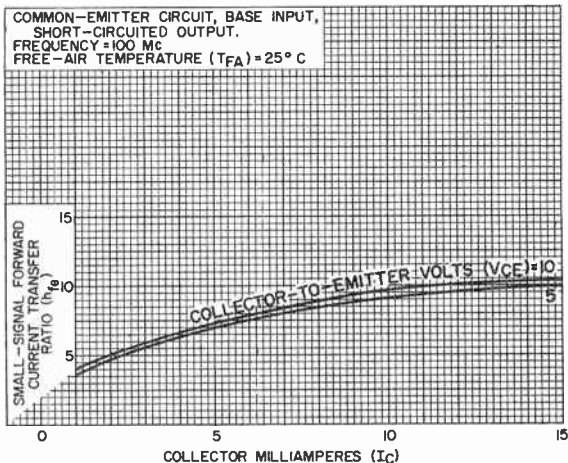
It is to be noted that the case of this transistor operates at the collector voltage. Because of the possibility of shock hazard when the case of this transistor is at a voltage appreciably above or below ground potential, suitable precautionary measures should be taken.



## POWER-OUTPUT-MEASUREMENT CIRCUIT

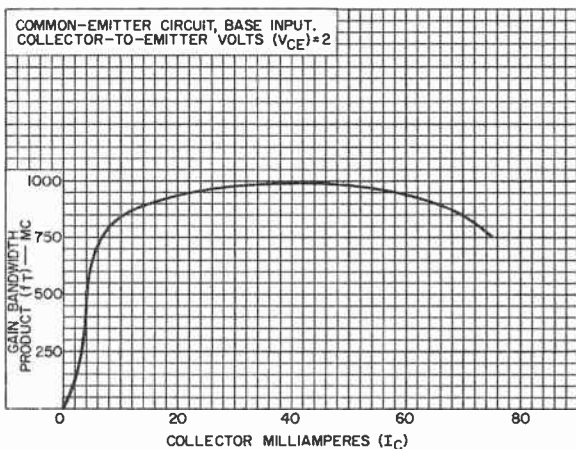


## TYPICAL SMALL-SIGNAL SHORT-CIRCUIT FORWARD-CURRENT TRANSFER RATIO CHARACTERISTIC



92CS-11777

## TYPICAL GAIN-BANDWIDTH-PRODUCT CHARACTERISTIC



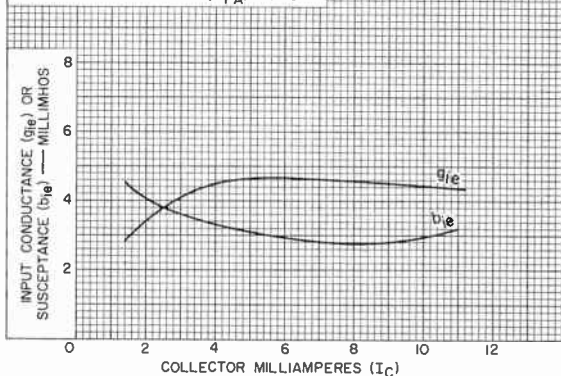
92CS-11773



# 2N2482

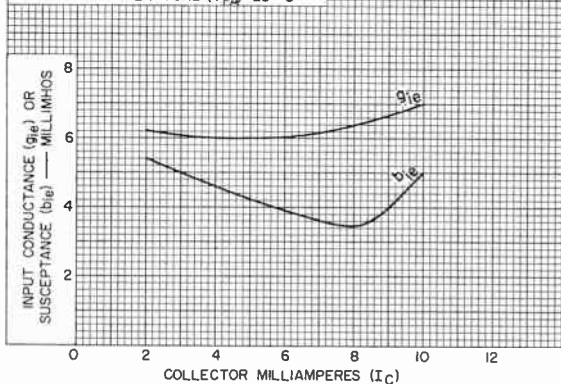
## TYPICAL SMALL-SIGNAL "Y" PARAMETER CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT,  
SHORT-CIRCUITED OUTPUT.  
FREQUENCY = 50 Mc  
COLLECTOR-TO-EMITTER VOLTS ( $V_{CE}$ ) = 5  
FREE-AIR TEMPERATURE ( $T_{FA}$ ) = 25° C



92CS-11764

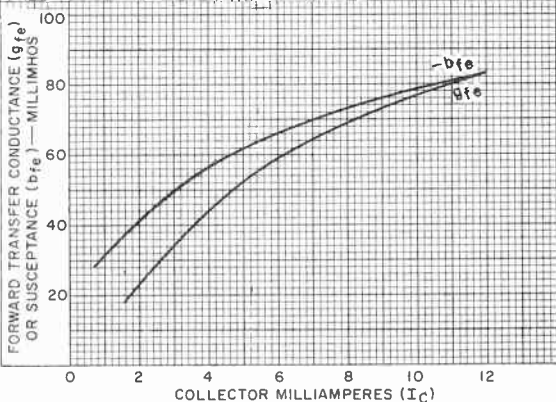
COMMON-EMITTER CIRCUIT, BASE INPUT,  
SHORT-CIRCUITED OUTPUT.  
FREQUENCY = 100 Mc  
COLLECTOR-TO-EMITTER VOLTS ( $V_{CE}$ ) = 5  
FREE-AIR TEMPERATURE ( $T_{FA}$ ) = 25° C



92CS-11765

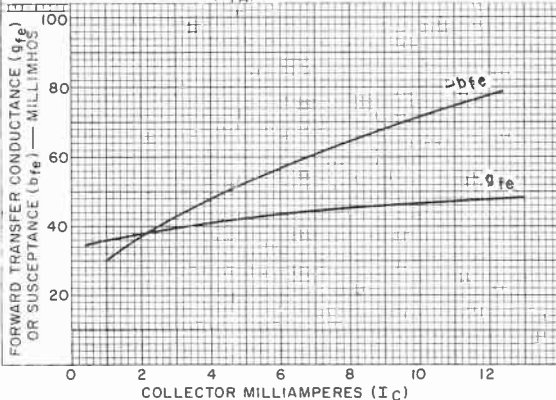
## TYPICAL SMALL-SIGNAL "Y" PARAMETER CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT, SHORT-CIRCUITED OUTPUT.  
COLLECTOR-TO-EMITTER VOLTS ( $V_{CE}$ )=5 FREQUENCY=50 Mc  
FREE-AIR TEMPERATURE ( $T_{FA}$ )= 25°C



92CS-11775

COMMON-EMITTER CIRCUIT, BASE INPUT, SHORT-CIRCUITED OUTPUT.  
COLLECTOR-TO-EMITTER VOLTS ( $V_{CE}$ )=5 FREQUENCY=70 Mc  
FREE-AIR TEMPERATURE ( $T_{FA}$ )= 25°C

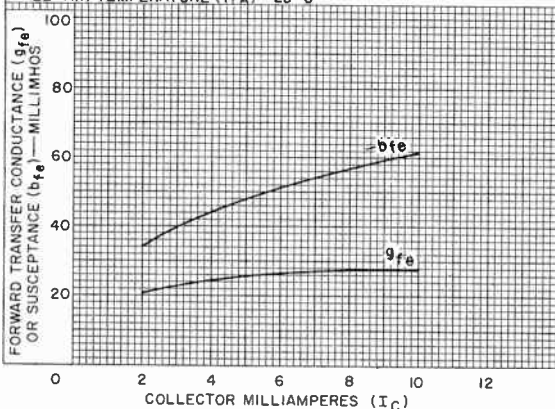


92CS-11774



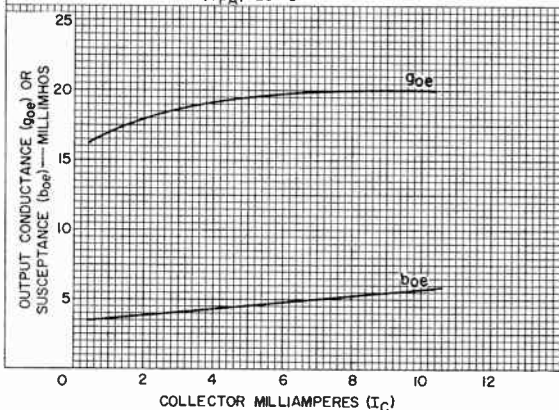
## TYPICAL SMALL-SIGNAL "Y" PARAMETER CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT, SHORT-CIRCUIED OUTPUT.  
COLLECTOR-TO-EMITTER VOLTS ( $V_{CE}$ )=5    FREQUENCY=100 Mc  
FREE-AIR TEMPERATURE ( $T_{FA}$ )=25°C



92CS-11776

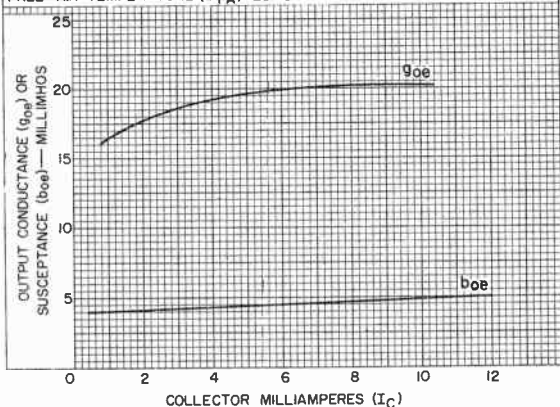
COMMON-EMITTER CIRCUIT, SHORT-CIRCUIED INPUT.  
COLLECTOR-TO-EMITTER VOLTS ( $V_{CE}$ )=5    FREQUENCY=50 Mc  
FREE-AIR TEMPERATURE ( $T_{FA}$ )=25°C



92CS-11770

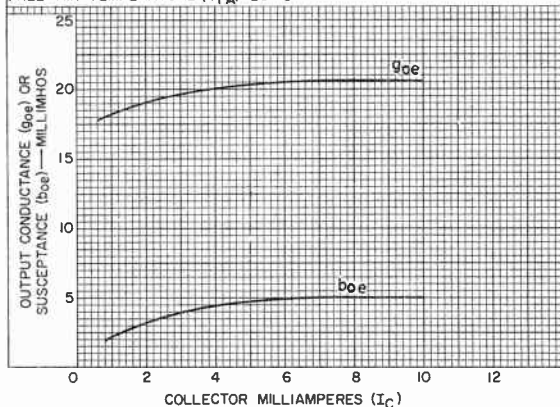
## TYPICAL SMALL-SIGNAL "Y" PARAMETER CHARACTERISTICS

COMMON-EMITTER CIRCUIT, SHORT-CIRCUITED INPUT.  
COLLECTOR-TO-EMITTER VOLTS ( $V_{CE}$ )=5      FREQUENCY=70 Mc  
FREE-AIR TEMPERATURE ( $T_{FA}$ )=25° C



92CS-11771

COMMON-EMITTER CIRCUIT, SHORT-CIRCUITED INPUT.  
COLLECTOR-TO-EMITTER VOLTS ( $V_{CE}$ )=5      FREQUENCY=100 Mc  
FREE-AIR TEMPERATURE ( $T_{FA}$ )=25° C



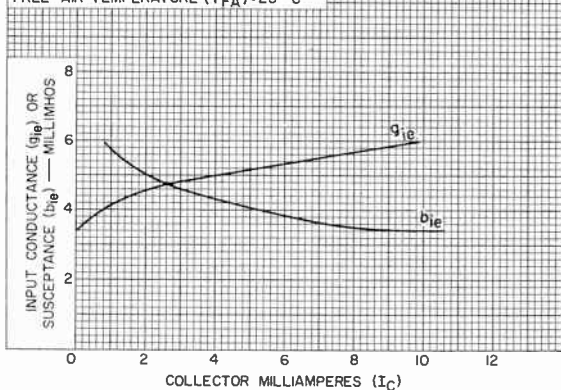
92CS-11772



# 2N2482

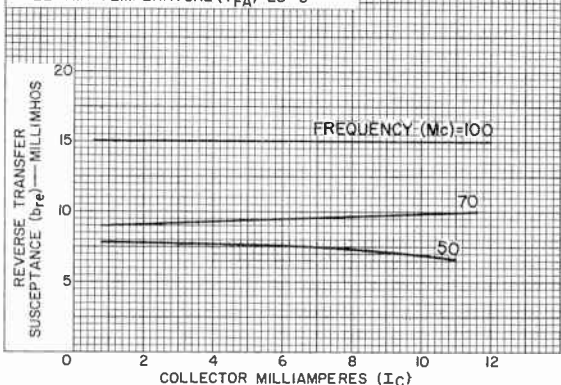
## TYPICAL SMALL-SIGNAL "Y" PARAMETER CHARACTERISTICS

COMMON-EMITTER CIRCUIT, BASE INPUT,  
SHORT-CIRCUITED OUTPUT.  
FREQUENCY = 70 Mc  
COLLECTOR-TO-EMITTER VOLTS ( $V_{CE}$ ) = 5  
FREE-AIR TEMPERATURE ( $T_{FA}$ ) = 25° C



92CS-11766

COMMON-EMITTER CIRCUIT, SHORT-  
CIRCUITED INPUT.  
COLLECTOR-TO-EMITTER VOLTS ( $V_{CE}$ ) = 5  
FREE-AIR TEMPERATURE ( $T_{FA}$ ) = 25° C



92CS-11763





## Triple Semiconductor Diode

GERMANIUM DIFFUSED-JUNCTION TYPE  
For Switching Applications in Elec-  
tronic Data-Processing Systems

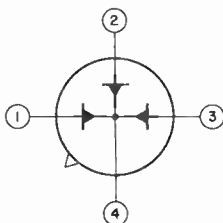
The 3DG001 is the same as the 2DG001 except for the following items:

### Mechanical:

Dimensional Outline. . . . . Similar to JEDEC No. TO-33  
Leads, Flexible. . . . . 4  
Minimum length . . . . . 1.5"  
Orientation and diameter . . . . . See *Dimensional Outline*

Terminal Diagram: **BOTTOM VIEW**

Lead 1 - Diode  
Unit  
No. 1  
Lead 2 - Diode  
Unit  
No. 3  
Lead 3 - Diode  
Unit  
No. 2



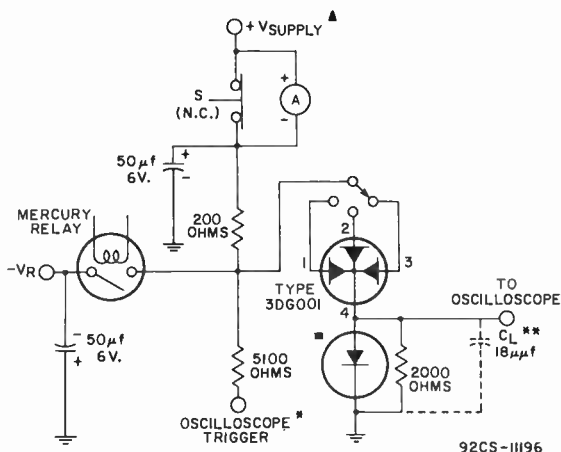
Lead 4 - Common  
Lead  
for  
Diode  
Units  
No. 1,  
No. 2,  
& No. 3

The arrow indicates direction of forward (easy) current flow as indicated by dc ammeter.



# 3DG001

## REVERSE-RECOVERY-TIME MEASUREMENT CIRCUIT



NOTE: THE STRAY CAPACITANCE ACROSS THE SOCKET FOR THE MULTIPLE-DIODE UNIT UNDER TEST MUST BE LESS THAN  $2 \mu\mu\text{f}$ .

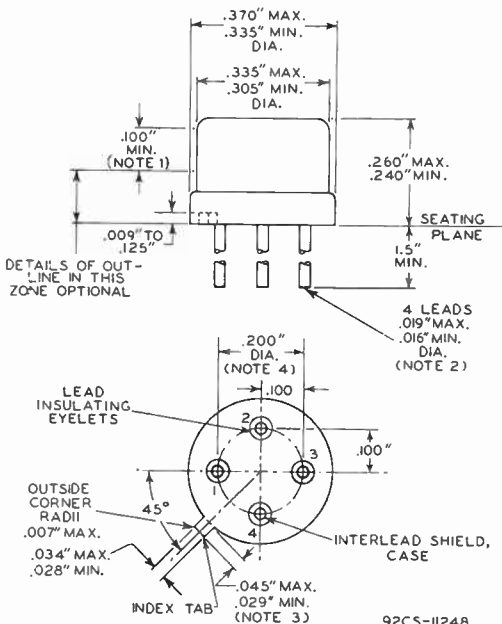
\* TEKTRONIX TYPE 545 OSCILLOSCOPE WITH TYPE H PLUG-IN VERTICAL AMPLIFIER AND TYPE P6000 PROBE, OR EQUIVALENT.

\*\*  $C_L$  REPRESENTS THE TOTAL CAPACITANCE ACROSS  $R_L$  — THAT IS, THE SUM OF THE OSCILLOSCOPE-PROBE CAPACITANCE AND THE STRAY CAPACITANCE. THE STRAY CAPACITANCE ACROSS  $R_L$  MUST BE LESS THAN  $6 \mu\mu\text{f}$ .

■ SILICON ULTRA-FAST SWITCHING DIODE WITH  $0.5\text{-}\mu\text{sec}$  MAXIMUM REVERSE RECOVERY TIME WHEN SWITCHING FROM 10 MA. FORWARD CURRENT TO  $-6$  VOLTS REVERSE VOLTAGE.

▲ WITH RELAY OUT AND SWITCH (S) OPEN, ADJUST  $V_{\text{SUPPLY}}$  TO OBTAIN SPECIFIED FORWARD CURRENT ( $I_F$ ).

SIMILAR TO JEDEC No. TO-33



NOTE 1: THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE VARIATION IN ACTUAL DIAMETER WITHIN THE ZONE SHALL NOT EXCEED 0.010".

NOTE 2: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE SEATING PLANE. BETWEEN 0.25" AND 1.5" A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

NOTE 3: MEASURED FROM MAXIMUM DIAMETER OF THE ACTUAL DEVICE.

NOTE 4: LEADS HAVING MAXIMUM DIAMETER (0.019") MEASURED IN GAUGING PLANE 0.054" + 0.001" - 0.000" BELOW THE SEATING PLANE OF THE DEVICE SHALL BE WITHIN 0.007" OF THEIR TRUE LOCATIONS RELATIVE TO A MAXIMUM-WIDTH TAB.





# Drift-Field Transistor

## With Two Emitters

### GERMANIUM P-N-P ALLOY TYPE

For Applications Requiring Control of an Output Current by Signals from Two Sources

#### GENERAL DATA

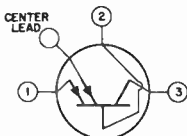
#### Electrical:

Maximum DC Collector-to-Base Voltage ( $V_{CB}$ ) with emitter No.1 and emitter No.2 connected together, for dc emitter-to-base volts = -0.5, dc collector $\mu a$ = -50, ambient temperature = 25° C. . . . .	-34	volts
Maximum DC Collector-Cutoff Current ( $I_{CBO}$ ) for dc collector-to-base volts = -12, emitter No.1 and emitter No.2 open, ambient temperature = 25° C. . . . .	-16	$\mu a$
Maximum DC Emitter-Cutoff Current ( $I_{EBO}$ ) with emitter No.1 and emitter No.2 connected together, for dc emitter-to-base volts = -0.5, collector open, ambient temperature = 25° C. . . . .	-16	$\mu a$
Thermal Resistance ( $R_T$ ):		
In free air. . . . .	400	°C/watt
With infinite heat sink. . . . .	100	°C/watt
Intrinsic Base Resistance ( $r_{bb}$ ) . . . . .	55	ohms
Collector-to-Base Capacitance ( $C_{ob}$ ) . . . . .	3.8	$\mu f$

#### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.405"
Maximum Diameter . . . . .	0.240"
Dimensional Outline . . . . .	JEDEC No. TO-44
Case . . . . .	Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	4
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See Dimensional Outline
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter No.1  
Center Lead - Emitter No.2



Lead 2 - Base  
Lead 3 - Collector (Adjacent to red dot on side of case)



## Maximum and Minimum Ratings, Absolute-Maximum Values:

DC COLLECTOR-TO-BASE VOLTAGE . . . . .	-34 max.	volts
DC EMITTER-NO.1-TO-BASE VOLTAGE . . . . .	-0.5 max.	volt
DC EMITTER-NO.2-TO-BASE VOLTAGE . . . . .	-0.5 max.	volt
DC COLLECTOR CURRENT . . . . .	-20 max.	ma
DC EMITTER CURRENT (Emitter No.1 & Emitter No.2) . . . . .	20 max.	ma
TRANSISTOR DISSIPATION: <sup>▲</sup>		
At ambient temperature of 25° C . . . . .	80 max.	mw
At ambient temperature of 55° C . . . . .	50 max.	mw
At ambient temperature of 71° C . . . . .	35 max.	mw
AMBIENT TEMPERATURE (During operation) . . . . .	71 max.	°C
STORAGE-TEMPERATURE RANGE . . . . .	-65 to +85	°C

## Characteristics, At Ambient Temperature of 25° C:

## Common-Base Circuit, Emitter Input

DC Collector-to-Base Voltage . . . . .	-12	volts
Small-Signal Current Transfer Ratio at 1 kc for:		
Emitter-No.1 ma. = 1 and Emitter-No.2 ma. = 0 . . . . .	0.985	
Emitter-No.1 ma. = 0 and Emitter-No.2 ma. = 1 . . . . .	0.985	
Alpha-Cutoff Frequency . . . . .	40	Mc

## Typical Operation, At Ambient Temperature of 25° C:

In accompanying common-base, emitter-input,  
1-Mc, capacitor-tuned, mixer-oscillator circuit

DC Collector-to-Base Voltage . . . . .	-4.4	volts
DC Emitter-No.1 (Signal-Emitter) Current . . . . .	1	ma
DC Emitter-No.2 (Oscillator-Emitter) Current . . . . .	0.5	ma
Input Impedance (Signal Emitter) . . . . .	25	ohms
Oscillator Voltage at Emitter No.2 . . . . .	80	mv
Conversion Power Gain (1 Mc to 455 kc) for emitter-No.1-to-collector load impedance (megohms) = 0.3 . . . . .	26	db

In accompanying common-base, emitter-input,  
1-Mc, inductance-tuned mixer-oscillator circuit

DC Collector-to-Base Voltage . . . . .	-10.5	volts
DC Emitter-No.1 (Signal-Emitter) Current . . . . .	1.1	ma
DC Emitter-No.2 (Oscillator-Emitter) Current . . . . .	0.42	ma
Input Impedance (Signal Emitter) . . . . .	23	ohms
Oscillator Voltage at Emitter No.2 . . . . .	145	mv
Conversion Power Gain (1 Mc to 262.5 kc) for emitter-No.1-to-collector load impedance (megohms) = 0.346 . . . . .	27	db

▲ See accompanying Rating Chart.



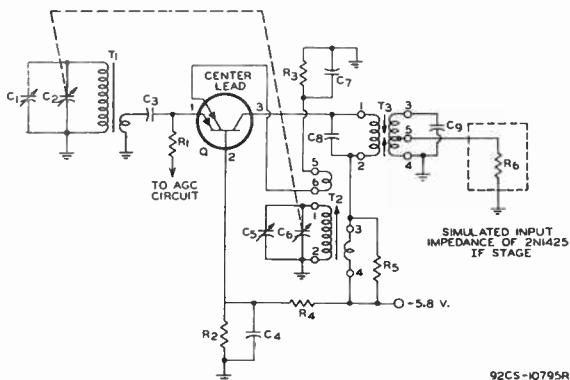
## OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The flexible leads of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation will crack the seals of the leads and damage the transistor.

When dip soldering is employed in the assembly of printed circuitry using this transistor, the temperature of the solder should not exceed 255° C for a maximum immersion period of 10 seconds.

## CAPACITOR-TUNED MIXER-OSCILLATOR CIRCUIT



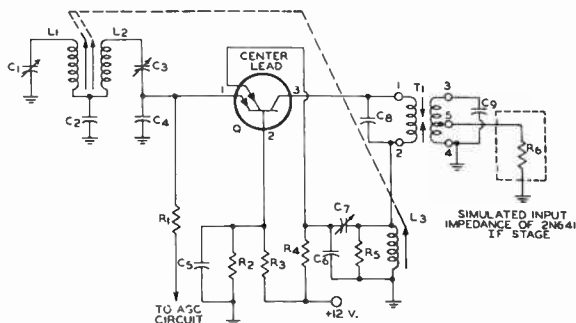
92CS-10795R1

- |  |   |
|--|---|
| C <sub>1</sub> :   | Q: Transistor type 3746                             |
| C <sub>5</sub> : Trimmer capacitors, 2-to-14 $\mu\text{f}$                                       | R <sub>1</sub> : 1200 ohms, 0.5 watt                |
| C <sub>2</sub> : Antenna tuning capacitor, 7-to-158 $\mu\text{f}$ , ganged with C <sub>6</sub>   | R <sub>2</sub> : 4700 ohms, 0.5 watt                |
| C <sub>3</sub> : 0.5 $\mu\text{f}$ , paper, 6 volts  | R <sub>3</sub> : 2200 ohms, 0.5 watt                |
| C <sub>4</sub> : 0.47 $\mu\text{f}$ , paper, 6 volts   | R <sub>4</sub> : 12,000 ohms, 0.5 watt              |
| C <sub>6</sub> : Oscillator tuning capacitor, 7-to-78 $\mu\text{f}$ , ganged with C <sub>2</sub> | R <sub>5</sub> : 3300 ohms, 0.5 watt                |
| C <sub>7</sub> : 0.005 $\mu\text{f}$ , paper, 6 volts  | R <sub>6</sub> : 1800 ohms                          |
| C <sub>8</sub> : 36 $\mu\text{f}$ , silver mica, 500 volts                                       | T <sub>1</sub> : Antenna transformer                |
| C <sub>9</sub> : 40 $\mu\text{f}$ , silver mica, 500 volts                                       | T <sub>2</sub> : Oscillator transformer             |
|  | T <sub>3</sub> : Intermediate-frequency transformer |

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## INDUCTANCE-TUNED MIXER-OSCILLATOR CIRCUIT

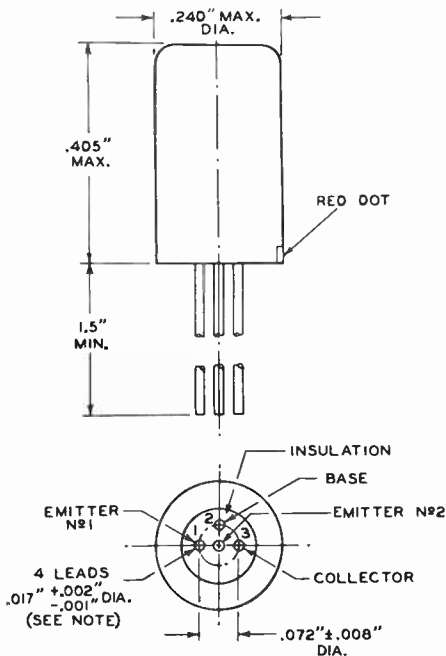


92CS-10794R1

- |  |  |
|--|--|
| $C_1$ : Trimmer capacitor, 50 $\mu\text{f}$ approx.  | $L_3$ : Oscillator coil                    |
| $C_2$ : 0.01 $\mu\text{f}$ , paper, 15 volts         | Q: Transistor type 3746                    |
| $C_3$ : Trimmer capacitor, 110 $\mu\text{f}$ approx. | $R_1$ : 1500 ohms, 0.5 watt                |
| $C_4$ : 0.005 $\mu\text{f}$ , paper, 15 volts        | $R_2$ : 22000 ohms, 0.5 watt               |
| $C_5$ : 0.2 $\mu\text{f}$ , paper, 15 volts          | $R_3$ : 5600 ohms, 0.5 watt                |
| $C_6$ : 0.0033 $\mu\text{f}$ , paper, 15 volts       | $R_4$ : 4700 ohms, 0.5 watt                |
| $C_7$ : Padder capacitor, 550 $\mu\text{f}$ approx.  | $R_5$ : 3300 ohms, 0.5 watt                |
| $C_8$ : 47 $\mu\text{f}$ , silver mica, 500 volts    | $R_6$ : 1400 ohms                          |
| $C_9$ : 50 $\mu\text{f}$ , silver mica, 500 volts    | $T_1$ : Intermediate-frequency transformer |
| $L_1$ :  |  |
| $L_2$ : Antenna-transformer windings                 |  |

Information furnished by RCA is believed to be accurate and reliable. However, no responsibility is assumed by RCA for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of RCA.



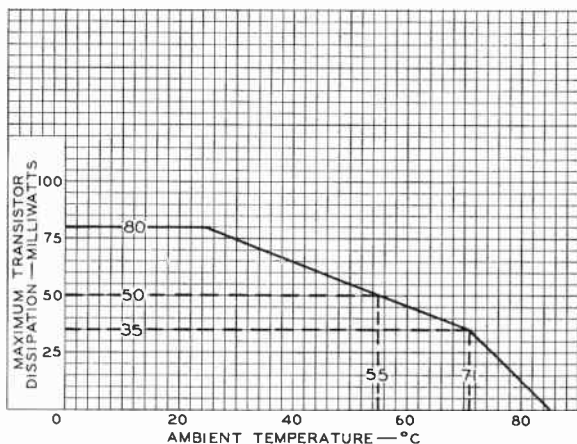


92CS-10798

NOTE: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE PLANE OF THE ACTUAL BOTTOM OF THE CASE. BETWEEN 0.25" AND 1.5", A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

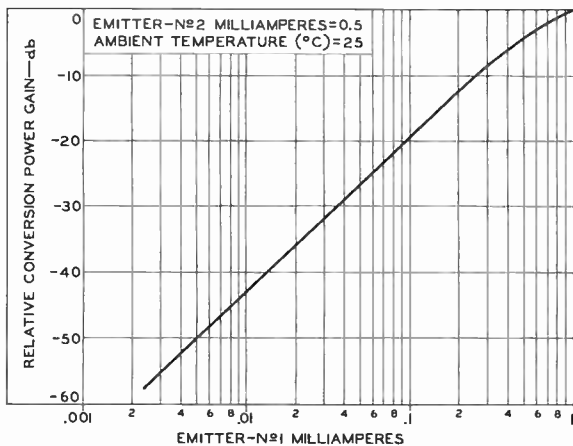


## RATING CHART



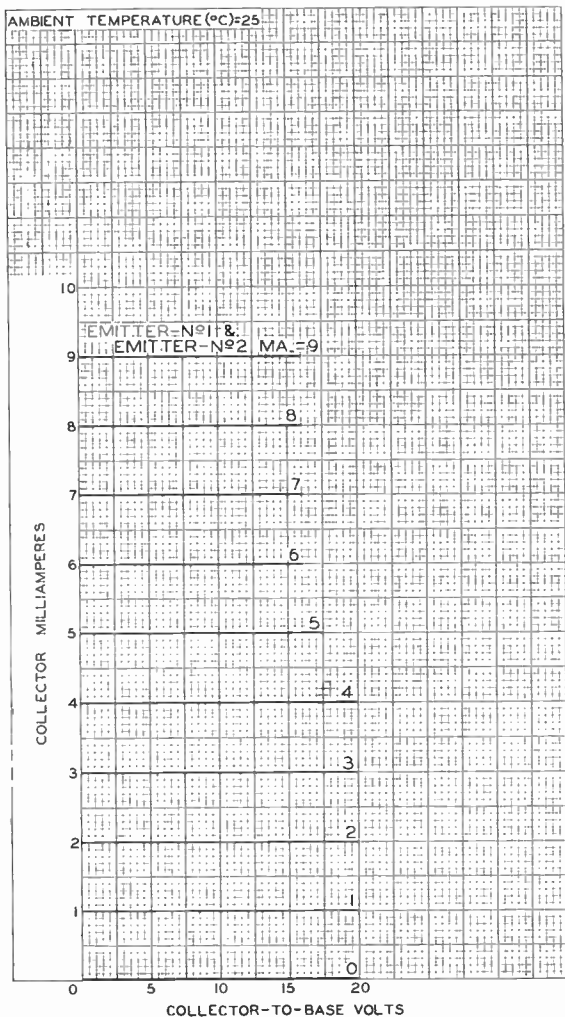
92CS-10788

## PERFORMANCE CHARACTERISTIC



92CS-10791

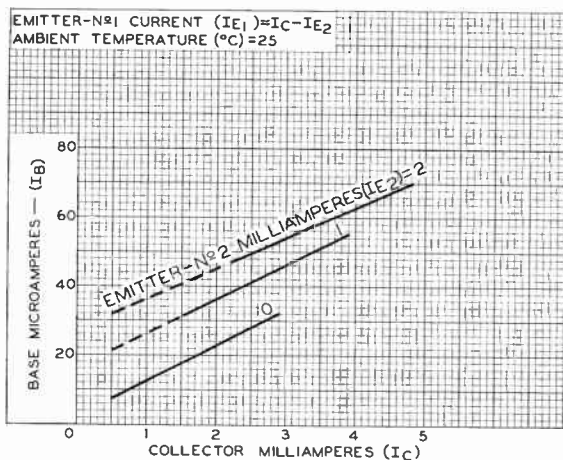
## TYPICAL COLLECTOR CHARACTERISTICS Common-Base Circuit



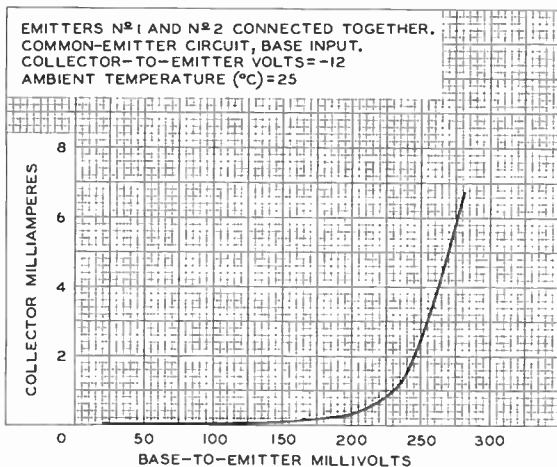
92CM-10793RI



## TYPICAL CHARACTERISTICS



92CS-10792



92CS-10796

# 3907 / 2N404

## Transistor

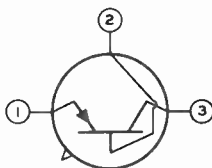
PREMIUM TYPE  
 GERMANIUM P-N-P ALLOY-JUNCTION TYPE  
 For Critical Computer Switching Applications

### GENERAL DATA

#### Mechanical:

Operating Position . . . . .	Any
Maximum Length (Excluding flexible leads) . . . . .	0.260"
Maximum Diameter . . . . .	0.370"
Dimensional Outline . . . . .	JEDEC No. TO-5
Case . . . . .	Welded, Metal
Seals . . . . .	Hermetic
Leads, Flexible . . . . .	3
Minimum length . . . . .	1.5"
Orientation and diameter . . . . .	See <i>Dimensional Outline</i>
Terminal Diagram:	BOTTOM VIEW

Lead 1 - Emitter  
 Lead 2 - Base



Lead 3 - Collector

### SWITCHING SERVICE

#### Maximum and Minimum Ratings, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE . . . . .	-25 max.	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With dc emitter-to-base volts = -1 . . . . .	-24 max.	volts
EMITTER-TO-BASE VOLTAGE . . . . .	-12 max.	volts
COLLECTOR CURRENT . . . . .	-200 max.	ma
EMITTER CURRENT . . . . .	200 max.	ma
TRANSISTOR DISSIPATION: <sup>a</sup>		
At ambient temperature of 25° C . . . . .	150 max.	mw
At ambient temperature of 55° C . . . . .	75 max.	mw
At ambient temperature of 71° C . . . . .	35 max.	mw
AMBIENT-TEMPERATURE RANGE:		
Operating . . . . .	-65 to +85	°C
Storage . . . . .	-65 to +100	°C
LEAD TEMPERATURE:		
For 10 seconds maximum . . . . .	235 max.	°C

<sup>a</sup> See accompanying Rating Chart.



# 3907/2N404

## ELECTRICAL CHARACTERISTICS

Voltage values are given with respect to base and ambient temperature of 25° C unless otherwise specified

Min. Typical Max.

DC Collector Breakdown Voltage for dc collector $\mu a = -20$ , dc emitter current = 0	$.BV_{CBO}$	-25	-45	-	volts
DC Emitter Breakdown Voltage for dc emitter $\mu a = -20$ , dc collector current = 0	$.BV_{EBO}$	-12	-30	-	volts
DC Emitter Floating Potential for dc collector volts = -25, dc emitter current = 0	$.V_{EBF}$	-	-	-1	volt
DC Base-to-Emitter Saturation Voltage: With dc collector ma. = -12, dc base ma. = -0.4	$V_{BE(sat)}$	-	-0.3	-0.35	volt
With dc collector ma. = -24, dc base ma. = -1		-	-0.32	-0.4	volt
DC Collector-to-Emitter Saturation Voltage: With dc collector ma. = -12, dc base ma. = -0.4	$V_{CE(sat)}$	-	-0.1	-0.15	volt
With dc collector ma. = -24, dc base ma. = -1		-	-0.12	-0.2	volt
DC Collector-Cutoff Current for dc collector volts = -12, dc emitter current = 0, ambient temperature of:	$I_{CBO}$				
25° C		-	-2	-5	$\mu a$
80° C		-	-45	-90	$\mu a$
DC Emitter Cutoff Current for emitter volts = -2.5, dc collector current = 0	$.I_{EBO}$	-	-1	-2.5	$\mu a$
DC Current Transfer Ratio: For dc collector-to-emitter volts = -0.15, dc collector ma. = -12	$h_{FE}$	30	45	-	
For dc collector-to-emitter volts = -0.2, dc collector ma. = -24		24	40	-	



Alpha-Cutoff Frequency for dc collector volts = -6, dc col- lector ma. = -1 . . . . .	$f_{ab}$	4	12	-	Mc
Output Capacitance for dc collector volts = -6, dc emitter cur- rent = 0 . . . . .	$C_{ob}$	-	15	20	$\mu\mu f$
Input Capacitance for dc emitter volts = -6, dc collector current = 0 . . . . .	$C_{ib}$	-	10	20	$\mu\mu f$
Stored Base Charge for dc collector ma. = 10, dc base ma. = 1 . . . . .	$Q_s$	-	1000	1400	$\mu\mu\text{Coulombs}$

### PERFORMANCE TESTS

This transistor type is tested in strict accordance with rigid procedures conforming with the mechanical, environmental and life requirements of Military Specification MIL-S-19500B.

### OPERATING CONSIDERATIONS

It is recommended that this transistor not be connected into or disconnected from circuits with the power on because high transient currents may cause permanent damage to the transistor.

The *flexible leads* of this transistor are usually soldered to the circuit elements. Soldering of the leads may be made close to the glass stem provided care is taken to conduct excessive heat away from the lead seal. Otherwise, the heat of the soldering operation may crack the glass seals of the leads and damage the transistor.

This transistor is intended for use in socketed, single-side printed circuit boards and in conventional wire-in type circuits. If this transistor is used in double-side printed-circuit boards or in printed-circuit boards utilizing eyelets, it may be necessary to use an insulating washer or similar standoff device made of good dielectric material to prevent the solder from shorting the leads to each other or to the board.

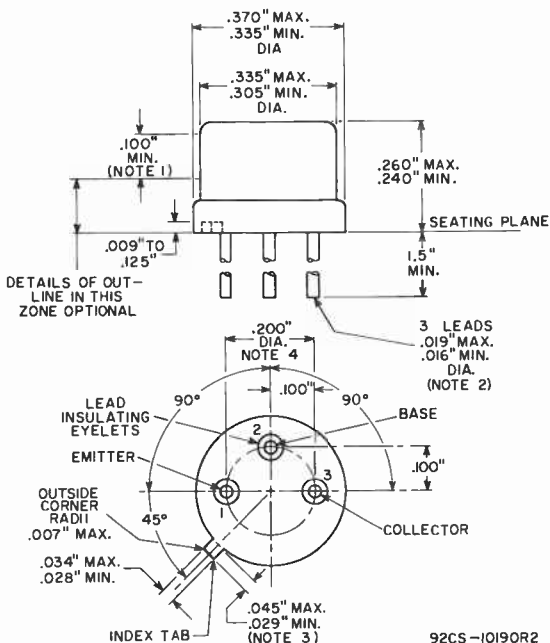
FOR ADDITIONAL INFORMATION ON THIS TYPE,  
WRITE FOR TECHNICAL BULLETIN AVAILABLE  
FROM:

Commercial Engineering  
Semiconductor & Materials Division  
RCA  
Somerville, New Jersey



# 3907 / 2N404

JEDEC No. T0-5



NOTE 1: THIS ZONE IS CONTROLLED FOR AUTOMATIC HANDLING. THE VARIATION IN ACTUAL DIAMETER WITHIN THE ZONE SHALL NOT EXCEED 0.010".

NOTE 2: THE SPECIFIED LEAD DIAMETER APPLIES IN THE ZONE BETWEEN 0.05" AND 0.25" FROM THE SEATING PLANE. BETWEEN 0.25" AND 1.5" A MAXIMUM DIAMETER OF 0.021" IS HELD. OUTSIDE OF THESE ZONES, THE LEAD DIAMETER IS NOT CONTROLLED.

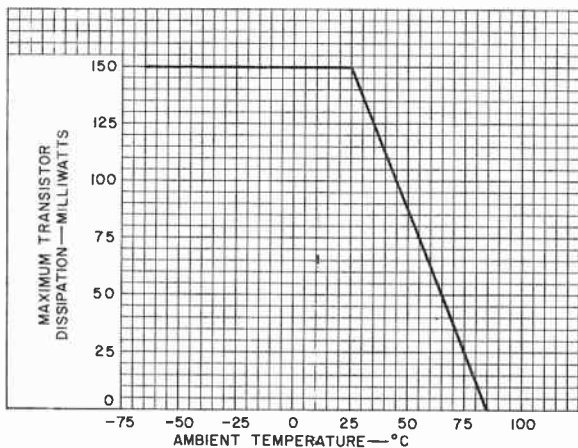
NOTE 3: MEASURED FROM MAXIMUM DIAMETER OF THE ACTUAL DEVICE.

NOTE 4: LEADS HAVING MAXIMUM DIAMETER (0.019") MEASURED IN GAUGING PLANE 0.054" + 0.001" - 0.000" BELOW THE SEATING PLANE OF THE DEVICE SHALL BE WITHIN 0.007" OF THEIR TRUE LOCATIONS RELATIVE TO A MAXIMUM-WIDTH TAB.



# 3907 / 2N404

## RATING CHART



92CS-10907RI



